## Eldo ${ }^{\circledR}$ User’s Manual

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## Table of Contents

Chapter 1
Introduction to Eldo ..... 31
Introduction ..... 31
Overview ..... 31
Eldo Input and Output Files ..... 32
Getting Started ..... 34
How to Run Eldo ..... 34
Schematic Example ..... 35
Associated Netlist ..... 35
Running a Simulation ..... 36
Related Documentation ..... 38
Documentation Conventions ..... 38
Chapter 2
Running Eldo. ..... 41
Running Eldo from the Command Line ..... 41
Viewing Eldo Documentation ..... 57
Command Line Help ..... 58
Multi-Threading Eldo Simulations ..... 58
Notes ..... 60
Eldo Initialization File ..... 60
Location Maps ..... 61
Location Map Structure ..... 62
eldo-stacktrace File ..... 63
Statistics File ..... 63
Generation ..... 64
Content ..... 64
Chapter 3
Eldo Control Language ..... 69
Introduction ..... 69
Overview of the .cir File Structure ..... 69
General Aspects of the Language Syntax ..... 70
First Line ..... 70
Continuation Lines ..... 70
Comment Lines ..... 70
Component Names ..... 71
Parameter Names ..... 71
String Parameters ..... 71
Reserved Keywords ..... 72
Node Name Conventions ..... 72
Values ..... 73
Model Names ..... 73
Scale Factors ..... 73
Directives ..... 74
Arithmetic Functions ..... 78
Operators ..... 82
Operator Precedence ..... 82
Arithmetic Operators ..... 83
Boolean Operators ..... 83
Bitwise Operators ..... 84
Expressions ..... 84
Simulation Counters ..... 86
Node and Element Information. ..... 86
Grounded Capacitors Information ..... 86
Matrix Information ..... 87
Newton Block Information ..... 87
Convergence Information ..... 87
Temperature Handling ..... 88
Devices ..... 89
Sources ..... 93
Macromodels ..... 97
Analog ..... 97
Digital ..... 100
Mixed ..... 101
Magnetic ..... 101
Switched Capacitor ..... 101
Commands ..... 102
Chapter 4
Device Models ..... 119
Summary ..... 119
Merging Devices in Parallel ..... 120
Device Models ..... 122
Resistor ..... 122
Resistor Model Syntax ..... 128
Capacitor ..... 133
Capacitor Model Syntax ..... 137
Inductor. ..... 140
Inductor Model Syntax ..... 145
Coupled Inductor ..... 147
RC Wire ..... 148
RC Wire Model Syntax ..... 150
Diffusion Resistor ..... 154
Diffusion Resistor Model Syntax ..... 154
Semiconductor Resistor ..... 156
Semiconductor Resistor Model Syntax ..... 156
Semiconductor Resistor Model Equations ..... 158
Transmission Line. ..... 163
Lossy Transmission Line ..... 165
Lossy Transmission Line: W Model ..... 181
Lossy Transmission Line: U Model ..... 192
Microstrip Models ..... 197
MTEE-Microstrip T Junction. ..... 198
MBEND—Microstrip Bend (Arbitrary Angle, Optimally Mitered) ..... 201
MBEND2-90-degree Microstrip Bend (Mitered) ..... 204
MBEND3-90-degree Microstrip Bend (Optimally Mitered) ..... 207
MCORN—90-degree Microstrip Bend (Unmitered) ..... 210
MSTEP-Microstrip Step in Width ..... 213
VIA2-Cylindrical Via Hole in Microstrip ..... 215
SBEND—Unmitered Stripline Bend ..... 218
STEE-Stripline T Junction ..... 221
SSTEP—Stripline Step in Width ..... 223
Junction Diode ..... 225
Diode Model Syntax ..... 228
Berkeley Level 1 (Eldo Level 1) ..... 229
Modified Berkeley Level 1 (Eldo Level 2) ..... 229
Fowler-Nordheim Model (Eldo Level 3) ..... 230
JUNCAP (Eldo Level 8) ..... 230
JUNCAP2 (Eldo Level 8, DIOLEV=11) ..... 231
Philips Diode Level 500 (Eldo Level 9) ..... 231
Diode Level 21 ..... 231
BJT—Bipolar Junction Transistor ..... 232
BJT Model Syntax ..... 235
Automatic Selection of BJT Model Via AREA Specifications ..... 236
Modified Gummel-Poon Model (Eldo Level 1) ..... 237
Philips Mextram 503.2 Model (Eldo Level 4) ..... 237
Improved Berkeley Model (Eldo Level 5) ..... 238
VBIC v1.2 Model (Eldo Level 8) ..... 238
VBIC v1.1.5 Model (Eldo Level 8) ..... 239
HICUM Model (Eldo Level 9) ..... 239
Philips Mextram 504 Model (Eldo Level 22) ..... 240
Philips Modella Model (Eldo Level 23) ..... 241
HICUM Level0 Model (Eldo Level 24) ..... 242
JFET-Junction Field Effect Transistor ..... 244
JFET Model Syntax ..... 246
MESFET—Metal Semiconductor Field Effect Transistor ..... 248
MOSFET. ..... 249
MOSFET Models ..... 252
Noise in MOSFETs ..... 256
Selection of MOSFET Models via W/L Specifications (Binning) ..... 257
MOS Parasitics Common Approach ..... 258
Berkeley SPICE Models ..... 265
MERCKEL MOSFET Models ..... 266
Berkeley SPICE BSIM1 Model (Eldo Level 8) ..... 267
Berkeley SPICE BSIM2 Model (Eldo Level 11) ..... 268
Modified Berkeley Level 2 (Eldo Level 12) ..... 269
Modified Berkeley Level 3 (Eldo Level 13) ..... 270
Modified Lattin-Jenkins-Grove Model (Eldo Level 16) ..... 270

## Table of Contents

Enhanced Berkeley Level 2 Model (Eldo Level 17) ..... 270
EKV MOS Model (Eldo Level 44 or EKV) ..... 271
Berkeley SPICE BSIM3v2 Model (Eldo Level 47) ..... 272
Berkeley SPICE BSIM3v3 Model (Eldo Level 53) ..... 273
Motorola SSIM Model (Eldo Level 54 or SSIM) ..... 276
Berkeley SPICE BSIMSOI3 v1.3 Model (Eldo Level 55) ..... 277
Berkeley SPICE BSIMSOI3 v2.x and v3.x Model (Eldo Level 56) ..... 279
Philips MOS 9 Model (Eldo Level 59 or MOSP9) ..... 283
Berkeley SPICE BSIM4 Model (Eldo Level 60) ..... 284
EKV3 MOS Model (Eldo Level 61 or EKV3) ..... 286
TFT Polysilicon Model (Eldo Level 62). ..... 286
Philips MOS Model 11 Level 1101 (Eldo Level 63) ..... 286
TFT Amorphous-Si Model (Eldo Level 64) ..... 287
Philips MOS Model 11 Level 1100 (Eldo Level 65) ..... 288
HiSIM Model (Eldo Level 66) ..... 289
SP Model (Eldo Level 67) ..... 290
Philips MOS Model 11 Level 1102 (Eldo Level 69) ..... 290
Philips PSP Model (Eldo Level 70) ..... 291
Philips MOS Model 20 Level 2002 (Eldo Level 71) ..... 292
Berkeley SPICE BSIMSOI4.0 Model (Eldo Level 72) ..... 292
HiSIM-LDMOS Model (Eldo Level 73) ..... 293
MOSVAR Model (Eldo Level 74) ..... 294
PSP103 Model (Eldo Level 75) ..... 295
HVMOS Model (Eldo Level 101) ..... 295
S-Domain Filter ..... 297
Z-Domain Filter ..... 299
Subcircuit Instance ..... 301
Chapter 5 ..... 307
Introduction ..... 307
Independent Sources ..... 307
Linear Dependent Sources ..... 308
Non-linear Dependent Sources ..... 308
S, Y, Z Parameter Extraction ..... 309
Independent Sources ..... 310
Independent Voltage Source ..... 310
Independent Current Source ..... 317
Amplitude Modulation Function ..... 323
Exponential Function ..... 325
Noise Function ..... 327
Noise Table Function ..... 330
Pattern Function ..... 332
Pulse Function ..... 336
Piece Wise Linear Function ..... 338
Single Frequency FM Function ..... 343
Sine Function ..... 344
Trapezoidal Pulse With Bit Pattern Function ..... 346
Exponential Pulse With Bit Pattern Function ..... 348
Dependent Sources ..... 350
Voltage Controlled Voltage Source ..... 350
Current Controlled Current Source ..... 358
Voltage Controlled Current Source ..... 363
Current Controlled Voltage Source ..... 371
S, Y, Z Parameter Extraction ..... 376
S, Y, Z Parameter Extraction ..... 376
Chapter 6
Analog Macromodels ..... 379
Eldo Analog Macromodels ..... 379
General Notes on the Use of FAS Macromodels ..... 380
Comparator ..... 381
Op-amp (Linear) ..... 384
Op-amp (Linear 1-pole) ..... 387
Application Area ..... 389
Op-amp (Linear 2-pole) ..... 391
Delay ..... 394
Saturating Resistor ..... 395
Voltage Limiter ..... 397
Current Limiter ..... 399
Voltage Controlled Switch ..... 401
Current Controlled Switch ..... 404
Ideal Single-Pole Multiple-Throw Switch ..... 407
Triangular to Sine Wave Converter ..... 409
Staircase Waveform Generator ..... 411
Sawtooth Waveform Generator ..... 413
Triangular Waveform Generator. ..... 415
Amplitude Modulator ..... 417
Pulse Amplitude Modulator ..... 419
Sample and Hold ..... 421
Track and Hold ..... 423
Pulse Width Modulator ..... 425
Voltage Controlled Oscillator ..... 428
Peak Detector ..... 430
Level Detector. ..... 433
Logarithmic Amplifier ..... 436
Anti-logarithmic Amplifier ..... 438
Differentiator ..... 440
Integrator ..... 442
Adder, Subtractor, Multiplier and Divider ..... 444
Chapter 7
Digital Macromodels ..... 447
Eldo Digital Macromodels ..... 447
Digital Model Definition. ..... 449
Delay ..... 453

## Table of Contents

Inverter ..... 454
Exclusive-OR Gate ..... 456
2-Input Digital Gates ..... 457
3-Input Digital Gates ..... 459
Multiple Input Digital Gates ..... 461
Mixed Signal Macromodels ..... 462
Analog to Digital Converter ..... 463
Digital to Analog Converter ..... 465
Chapter 8
Magnetic Macromodels ..... 467
Eldo Magnetic Macromodels ..... 467
Transformer Winding ..... 468
Non-linear Magnetic Core 1 ..... 470
Non-linear Magnetic Core 2 ..... 473
Linear Magnetic Core ..... 476
Magnetic Air Gap ..... 477
Transformer (Variable \# of Windings) ..... 478
Ideal Transformer ..... 480
Chapter 9Switched Capacitor Macromodels.481
Introduction ..... 481
Switch Level Representation ..... 481
Macromodels ..... 481
Operational Amplifier ..... 483
Switch ..... 488
Z-domain Representation ..... 491
General Notes on the Use of Macromodels ..... 491
Ideal Operational Amplifier ..... 492
SC Integrators \& LDI's ..... 493
Inverting Switched Capacitor ..... 495
Non-inverting Switched Capacitor ..... 498
Parallel Switched Capacitor ..... 501
Serial Switched Capacitor. ..... 503
Serial-parallel Switched Capacitor ..... 505
Bi-linear Switched Capacitor ..... 508
Unswitched Capacitor ..... 510
Applications ..... 512
Non-inverting Integrator. ..... 513
LDI Phase Control Non-inverting Integrator ..... 514
Euler Forward Integrator ..... 515
LDI Phase Control Euler Forward Integrator ..... 516
Euler Backward Integrator ..... 517
LDI Phase Control Euler Backward Integrator ..... 518
Tutorial-SC Low Pass Filter ..... 518
Chapter 10
Simulator Commands ..... 519
Command Summary ..... 519
Analysis Commands ..... 519
Display Commands ..... 521
Simulation Control Commands ..... 522
Circuit Description Commands. ..... 524
Command Line Help ..... 527
Command Descriptions ..... 527
.A2D ..... 528
.AC ..... 538
.ADDLIB ..... 544
.AGE ..... 546
.AGE_LIB ..... 547
.AGEMODEL ..... 548
.ALTER ..... 549
.BIND ..... 554
BINDSCOPE ..... 558
.CALL_TCL ..... 559
.CHECKBUS ..... 561
CHECKSOA ..... 564
CHRENT ..... 567
CHRSIM ..... 569
COMCHAR ..... 571
CONNECT. ..... 573
.CONSO ..... 574
.CORREL ..... 575
.D2A ..... 577
.DATA ..... 585
.DC ..... 588
.DCHIZ ..... 595
.DCMISMATCH ..... 596
.DEFAULT ..... 600
DEFMAC ..... 601
DEFMOD ..... 603
.DEFPLOTDIG ..... 604
DEFWAVE ..... 605
.DEL ..... 610
.DEX ..... 611
.DISCARD ..... 612
.DISFLAT ..... 613
.DISTRIB ..... 614
.DSP ..... 615
.DSPF_INCLUDE ..... 617
.DSPMOD ..... 625
.END ..... 631
.ENDL ..... 632
.ENDS ..... 633

## Table of Contents

.EQUIV ..... 634
.EXTMOD ..... 636
.EXTRACT ..... 637
.FFILE ..... 667
FILTER ..... 669
.FORCE ..... 672
.FOUR ..... 673
.FUNC ..... 675
.GLOBAL ..... 676
.GUESS ..... 677
.HDL ..... 678
HIER ..... 680
.IC ..... 682
.IGNORE_DSPF_ON_NODE ..... 684
INCLUDE ..... 685
.INIT ..... 688
.IPROBE ..... 689
.LIB ..... 692
.LOAD ..... 698
.LOOP ..... 699
.LOTGROUP ..... 701
.LSTB ..... 703
.MALIAS ..... 704
.MAP_DSPF_NODE_NAME ..... 705
.MC ..... 706
.MCMOD ..... 715
.MEAS ..... 717
.MODDUP ..... 722
.MODEL ..... 723
.MODLOGIC ..... 727
.MONITOR ..... 728
.MPRUN ..... 729
.MSELECT ..... 737
.NET ..... 740
.NEWPAGE ..... 741
.NOCOM ..... 742
.NODESET ..... 743
.NOISE ..... 744
.NOISE_CORREL ..... 746
.NOISETRAN ..... 747
.NOTRC ..... 752
.NWBLOCK ..... 753
.OBJECTIVE ..... 754
.OP ..... 755
.OP_DISPLAY ..... 761
.OPTFOUR ..... 764
OPTIMIZE ..... 770
OPTION ..... 771
.OPTNOISE ..... 772
OPTPWL ..... 776
OPTWIND ..... 777
PARAM ..... 778
PARAMDEX ..... 788
PARAMOPT ..... 789
PART ..... 790
PLOT ..... 791
PLOTBUS ..... 827
PRINT ..... 830
PRINTBUS ..... 832
PRINTFILE ..... 835
.PROBE ..... 838
.PROBEBUS ..... 848
.PROTECT ..... 850
.PZ ..... 851
.RAMP ..... 852
.RESTART ..... 854
.SAVE ..... 857
.SCALE ..... 860
.SELECT_DSPF_ON_NODE ..... 862
.SENS ..... 863
.SENSAC ..... 865
.SENSPARAM ..... 867
.SETBUS ..... 870
.SETKEY ..... 871
.SETSOA ..... 872
SIGBUS ..... 880
.SINUS ..... 884
SNF ..... 885
.SOLVE ..... 887
START TIME ..... 889
STEP ..... 890
SUBCKT ..... 898
SUBDUP ..... 904
TABLE ..... 905
TCL_WAVE ..... 906
TEMP ..... 907
TF ..... 908
TITLE ..... 909
TOPCELL ..... 910
TRAN ..... 911
TSAVE ..... 916
TVINCLUDE ..... 918
UNPROTECT ..... 925
USE ..... 926
USEKEY ..... 928
USE_TCL ..... 929
USE_VERILOGA ..... 931
VEC ..... 932

## Table of Contents

VERILOG ..... 933
WCASE ..... 934
WIDTH ..... 938
Chapter 11
Simulator and Control Options ..... 939
Introduction ..... 939
Eldo Options ..... 940
.OPTION ..... 940
Cadence Compatibility Options ..... 949
SPICE Compatibility Options ..... 949
Simulator Compatibility Options ..... 950
Netlist Parser Control Options ..... 950
Simulation Speed, Accuracy and Efficiency Options ..... 963
Miscellaneous Simulation Control Options ..... 974
Model Control Options ..... 983
Reduction Options ..... 993
Noise Analysis Options ..... 994
Simulation Display Control Options ..... 995
Simulation Output Control Options ..... 997
Optimizer Output Control Options .....  1008
File Generation Options ..... 1010
Mathematical Algorithm Options ..... 1015
Mixed-Mode Options ..... 1018
Other Options ..... 1021
Chapter 12
Transient Noise Analysis ..... 1023
Introduction to Transient Noise Analysis ..... 1023
.NOISETRAN Command ..... 1025
Example 1-High-rate Particle Detector ..... 1026
Description of the Particle Detector Behavior ..... 1026
Analysis of the Noise Performance. ..... 1027
Netlist for Example 1 ..... 1030
Example 2-Switched Capacitor Filter ..... 1031
Characterization of the Amplifier ..... 1032
Netlist Used for the Amplifier Simulations ..... 1034
Switch Noise Model ..... 1036
Simulation Results of the Complete Circuit ..... 1036
Netlist for Example 2 ..... 1038
Chapter 13
Working with S, Y, Z Parameters ..... 1041
Introduction ..... 1041
Simulation Setup for S, Y, Z Parameter Extraction ..... 1041
S, Y, Z Parameter Extraction ..... 1042
Matrix Parameter Extraction ..... 1044
Output File Specification ..... 1045
Transient Simulation of Circuits Characterized in the Frequency Domain ..... 1047
Introduction ..... 1047
Technical Background ..... 1048
Implementation Issues ..... 1051
Applications ..... 1052
Functionality ..... 1053
Instantiating a Block Defined by S-Parameters ..... 1054
Touchstone Data Format ..... 1058
Mixed Mode S-Parameter Extraction ..... 1059
Chapter 14
Speed and Accuracy ..... 1061
Introduction ..... 1061
Speed and Accuracy in Eldo ..... 1062
Integration Methods ..... 1062
Time Step Control ..... 1064
Newton Iterations Accuracy Control ..... 1070
Global Tuning of the Accuracy-EPS ..... 1070
Global Tuning of the Accuracy-TUNING ..... 1071
IEM Algorithm ..... 1072
OSR Algorithm ..... 1073
Simulation of Large Circuits ..... 1076
Tips for Troubleshooting and/or Improving Convergence and Performance ..... 1079
Operating Point Calculation ..... 1079
.SAVE, .USE \& .RESTART ..... 1080
Chapter 15
Eldo Reduction ..... 1085
Introduction ..... 1085
Basic Reduction ..... 1086
Advanced Reduction ..... 1086
Main Parameters Controlling the Reduction Process ..... 1086
Reduction Output ..... 1087
Generic Reduction Command ..... 1088
.REDUCE ANALOG ..... 1088
TICER Reduction Command ..... 1091
REDUCE TICER ..... 1091
Reduction Command for Resistive Networks ..... 1094
REDUCE RONLY ..... 1094
Reduction Command for Coupled Capacitances ..... 1095
.REDUCE CC ..... 1095
Reduction Options ..... 1097
Specifying the Network Type for Reduction ..... 1097
Controlling the Effects of Reduction on Circuit Topology ..... 1097
Chapter 16
Integral Equation Method (IEM) ..... 1099
Introduction ..... 1099

## Table of Contents

Application Domains ..... 1099
Circuit Elements Supported-Limitations ..... 1099
Use of IEM, Tolerance Parameters ..... 1100
Efficient Usage of IEM ..... 1102
Examples for IEM ..... 1102
Introduction ..... 1102
Stability ..... 1103
Example 1-bjtinv ..... 1103
Example 2-ivdd ..... 1105
Accuracy ..... 1108
Example 3-oscil ..... 1108
Example 4-moy1 ..... 1112
Speed ..... 1114
Example 5-ladder ..... 1114
Example 6-opamp_5pin ..... 1116
Chapter 17
Pole-Zero Post-Processor ..... 1121
Introduction ..... 1121
Running the Dialog for Pole-Zero Analysis ..... 1122
Frequency Limit ..... 1123
Pole-Zero Cancellation by Threshold ..... 1123
Hand Selection ..... 1124
Select Index ..... 1124
FNS Model. ..... 1125
Pole-Zero Numerical Issues ..... 1126
Chapter 18
Optimizer in Eldo ..... 1127
Introduction ..... 1127
Overview ..... 1127
Problem Statement ..... 1128
Invoking the Eldo Optimizer ..... 1129
Exploiting the Results of Optimization ..... 1129
Optimization Commands ..... 1130
.EXTRACT and .MEAS ..... 1131
.OBJECTIVE ..... 1134
OPTIMIZE ..... 1138
.PARAMOPT ..... 1142
Optimization Options ..... 1147
Basic Examples of Circuit Optimization ..... 1149
Designing a Low Noise Amplifier (LNA) ..... 1149
Fourband Filter Optimization ..... 1156
MOS Characterization ..... 1159
Robust Optimization Using Corners ..... 1162
Set-up Time Computation ..... 1164
Modeling Capabilities in Eldo and Optimization ..... 1165
What Problems can be Solved?. ..... 1167
Minimization and Maximization of Objectives ..... 1179
Goal Values for Objectives ..... 1181
Range Constraints on Objectives ..... 1183
The Optimization Methods ..... 1185
Eldo Optimizer/SQP Method ..... 1185
Eldo Optimizer/Search Method ..... 1189
Exploiting Output Results ..... 1190
Binary Output ..... 1191
ASCII Output for Eldo Optimizer/SQP ..... 1191
References ..... 1205
Chapter 19
Monte Carlo Analysis ..... 1207
Introduction ..... 1207
Usage ..... 1208
Define the .MC Command ..... 1208
Assign Nominal Parameter Values ..... 1211
LOT/DEV Correlation ..... 1212
Define Monte Carlo Parameters ..... 1213
Monte Carlo Output ..... 1215
Examples ..... 1221
Chapter 20
Statistical Experimental Design and Analysis ..... 1227
Introduction ..... 1227
Overview ..... 1227
Practicalities ..... 1227
Main Effects Analysis and .WCASE Command ..... 1228
Analysis Statement ..... 1229
Running the Experiment ..... 1230
Commands ..... 1230
.DEX ..... 1231
.PARAMDEX ..... 1239
Examples of Experimental Design. ..... 1252
References ..... 1252
Chapter 21
Reliability Simulation ..... 1253
Introduction ..... 1253
Running Reliability Simulation in Eldo ..... 1253
Chapter 22
Post-Processing Library ..... 1255
Introduction ..... 1255
General Usage ..... 1255
Registering User Defined Functions inside Eldo ..... 1255
Macro-Like Usage of UDF ..... 1255
Keyword Parameters ..... 1256

## Table of Contents

Making Specific Calls to UDF inside Eldo. ..... 1257
Working with Waveforms inside UDF ..... 1257
evalExpr ..... 1259
defineVec ..... 1260
Example Files ..... 1260
Built-In Waveform Functions ..... 1261
Eldo Functions ..... 1262
RF Functions ..... 1271
Built-In DSP Functions ..... 1272
Accessing Waves Inside an External Database ..... 1280
Miscellaneous Commands ..... 1281
Chapter 23
IBIS Models Support in Eldo. ..... 1285
Introduction ..... 1285
IBIS Background ..... 1285
Using IBIS Models in Eldo. ..... 1285
IBIS Resources on the Web ..... 1286
IBIS File Types and Structures ..... 1286
Checking IBIS Files with the Golden Parser ..... 1287
IBIS Device Standards ..... 1288
Buffers. ..... 1288
Package ..... 1298
Component ..... 1298
Electrical Board Description ..... 1300
IBIS Support in Eldo ..... 1301
Analysis Types ..... 1301
Digital Levels ..... 1301
IBIS Buffers ..... 1302
IBIS Component ..... 1313
IBIS Package ..... 1319
Electrical Board Description ..... 1321
Supported Keywords and Sub-Parameters ..... 1324
IBIS Tutorials ..... 1330
Tutorial 1—Single-Ended Tx-Rx System ..... 1330
Tutorial 2—Pseudo-Differential Tx-Rx System ..... 1332
Tutorial 3-Package Parasitics Cross Talk ..... 1335
Tutorial 4-Simultaneous Switching Output Noise ..... 1337
Chapter 24
Tutorials ..... 1341
Introduction ..... 1341
Tutorial \#1—Parallel LCR Circuit. ..... 1342
Netlist Explanation ..... 1343
Simulation Results ..... 1344
Tutorial \#2-4th Order Butterworth Filter ..... 1345
Netlist Explanation ..... 1345
Simulation Results-1 ..... 1347
Simulation Results-2 ..... 1348
Tutorial \#3-Band Pass Filter ..... 1349
Netlist Explanation ..... 1350
Simulation Results ..... 1352
Tutorial \#4—Low Pass Filter. ..... 1353
Netlist Explanation ..... 1354
Simulation Results ..... 1355
Tutorial \#5-Colpitts Oscillator ..... 1356
Netlist Explanation ..... 1357
Simulation Results ..... 1358
Tutorial \#6-High Voltage Cascade ..... 1359
Netlist Explanation ..... 1360
Simulation Results-1 ..... 1361
Simulation Results-2 ..... 1362
Tutorial \#7-Non-inverting Amplifier ..... 1363
Netlist Explanation ..... 1364
Simulation Results ..... 1365
Tutorial \#8-Bipolar Amplifier. ..... 1366
Netlist Explanation ..... 1367
Simulation Results ..... 1368
Tutorial \#9—SC Low Pass Filter. ..... 1369
Simulation Results-1 ..... 1370
Simulation Results-2 ..... 1371
Chapter 25
Simulator Compatibility. ..... 1373
Introduction ..... 1373
HSPICE Compatibility ..... 1373
Devices ..... 1374
Commands ..... 1376
Options ..... 1378
Netlist ..... 1381
Arithmetic Functions and Operators ..... 1383
Output Format ..... 1383
TIspice Compatibility ..... 1384
Devices ..... 1384
Commands ..... 1386
Netlist ..... 1391
Functions and Sources ..... 1391
Dangling Nets Options ..... 1392
Eldo Extensions for TIspice Compatibility. ..... 1392
Spectre Compatibility ..... 1395
Usage. ..... 1395
Description ..... 1396
Troubleshooting ..... 1399
Spectre to Eldo Converter ..... 1402
Appendix A
Error Messages ..... 1411
Error Message Classification ..... 1411
Warnings ..... 1411
Syntax Errors ..... 1411
Effects ..... 1411
Error Messages ..... 1412
Global Errors ..... 1412
Errors Related to Nodes ..... 1415
Errors Related to Objects ..... 1416
Errors Related to Commands ..... 1423
Errors Related to Models ..... 1430
Errors Related to AMODELS ..... 1431
Errors Related to Subcircuits ..... 1432
Miscellaneous Errors ..... 1432
Warning Messages ..... 1436
Global Warnings ..... 1436
Warnings Related to Nodes ..... 1439
Warnings Related to Objects ..... 1440
Warnings Related to Commands ..... 1443
Warnings Related to Models. ..... 1448
Warnings Related to Subcircuits ..... 1450
Miscellaneous Warnings ..... 1450
Appendix B
Troubleshooting ..... 1457
Introduction ..... 1457
Common Netlist Errors ..... 1457
Appendix C
Examples ..... 1459
Introduction ..... 1459
Example\#1—SC Schmitt Trigger ..... 1460
Simulation Results ..... 1461
Example\#2-4-bit Adder ..... 1461
Simulation Results ..... 1464
Example\#3-CMOS Op-amp (Open Loop) ..... 1465
Simulation Results ..... 1467
Example\#4-CMOS Op-amp (Closed Loop) ..... 1467
Simulation Results ..... 1469
Example\#5-5th Order Elliptic SC Low Pass Filter ..... 1469
Simulation Results ..... 1472
Example\#6-Charge Control in MOS 4 and 6 ..... 1472
Simulation Results ..... 1474
Example\#7—Active RC Band Pass Filter ..... 1474
Simulation Results ..... 1477
Example\#8-2nd Order Delta Sigma Modulator ..... 1477
Simulation Results ..... 1480
Example\#9-Operational Amplifier ..... 1480
Simulation Results-1 ..... 1481
Simulation Results-2 (Zoom) ..... 1482
Appendix D
Eldo Interactive Mode ..... 1483
Introduction ..... 1483
To Read Information ..... 1484
To Reset Several Features ..... 1487
Options ..... 1487
Change Features ..... 1488
To Control Execution ..... 1492
Appendix E
Eldo Utilities ..... 1495
Utility to Convert .chi to .cir ..... 1495
Utility to Convert VCD to Test Vectors ..... 1496
Utility to Convert a Waveform Database ..... 1497
Appendix F
Eldo Encryption ..... 1499
Eldo Encryption ..... 1499
Protection of Encrypted Libraries ..... 1501
Overview ..... 1501
Coding and Encrypting a Protected Library ..... 1502
Description of the Loading and Control Process ..... 1503
Creating the IP Access Library ..... 1504
Installing a Protected Library ..... 1506
List of Errors and Warnings ..... 1506
Appendix G
STMicroelectronics Models ..... 1509
Introduction ..... 1509
How to Invoke Eldo-ST ..... 1509
What Does it Change? ..... 1509
STMicroelectronics Version of Eldo ..... 1510
Index
End-User License Agreement

## List of Figures

Figure 1-1. Eldo Input \& Output Files ..... 32
Figure 1-2. Cascaded Inverter Circuit ..... 35
Figure 1-3. Inverter Subcircuit. ..... 35
Figure 1-4. EZwave output (.wdb). ..... 37
Figure 4-1. Coupled Inductor. ..... 147
Figure 4-2. Cross-Sectional View of Diffused Resistor ..... 157
Figure 4-3. Microstrip Line Structure ..... 176
Figure 4-4. Covered Pair Microstrip Line Structure ..... 176
Figure 4-5. Stripline Structure ..... 176
Figure 4-6. Microstrip T Junction ..... 198
Figure 4-7. Microstrip T Junction Symbol ..... 198
Figure 4-8. Equivalent circuit Microstrip T Junction ..... 199
Figure 4-9. Microstrip Bend (Arbitrary Angle, Optimally Mitered) ..... 201
Figure 4-10. Microstrip Bend (Arbitrary Angle, Optimally Mitered) Symbol ..... 201
Figure 4-11. Equivalent circuit Microstrip Bend (Arbitrary Angle, Optimally Mitered) ..... 202
Figure 4-12. 90-degree Microstrip Bend (Mitered) ..... 204
Figure 4-13. 90-degree Microstrip Bend (Mitered) Symbol ..... 204
Figure 4-14. Equivalent circuit MBEND2 ..... 205
Figure 4-15. 90-degree Microstrip Bend (Optimally Mitered) ..... 207
Figure 4-16. 90-degree Microstrip Bend (Optimally Mitered) Symbol ..... 207
Figure 4-17. Equivalent Circuit MBEND3 ..... 208
Figure 4-18. 90-degree Microstrip Bend (Unmitered) ..... 210
Figure 4-19. 90-degree Microstrip Bend (Unmitered) Symbol ..... 210
Figure 4-20. Equivalent circuit Microstrip corner ..... 211
Figure 4-21. Microstrip Step in Width ..... 213
Figure 4-22. Microstrip Step in Width Symbol ..... 213
Figure 4-23. Equivalent circuit of a microstrip step in width ..... 214
Figure 4-24. Cylindrical Via Hole in Microstrip ..... 215
Figure 4-25. Cylindrical Via Hole in Microstrip Symbol ..... 215
Figure 4-26. Equivalent circuit Cylindrical Via Hole in Microstrip ..... 216
Figure 4-27. Unmitered Stripline Bend ..... 218
Figure 4-28. Unmitered Stripline Bend Symbol ..... 218
Figure 4-29. Equivalent circuit of an unmitered stripline bend ..... 219
Figure 4-30. Stripline T Junction ..... 221
Figure 4-31. Stripline T Junction Symbol ..... 221
Figure 4-32. Stripline Step in Width ..... 223
Figure 4-33. Stripline Step in Width Symbol ..... 223
Figure 4-34. Equivalent circuit for a Stripline Step in Width ..... 224
Figure 5-1. AM Function Example ..... 324
Figure 5-2. Exponential Function ..... 326
Figure 5-3. Noise Function ..... 328
Figure 5-4. Pattern Function ..... 334
Figure 5-5. Pulse Function ..... 336
Figure 5-6. Voltage Source Characteristics ..... 337
Figure 5-7. Piece Wise Linear Function ..... 340
Figure 5-8. Piece Wise Linear Function Example 1 ..... 340
Figure 5-9. Piece Wise Linear Function Example 2 ..... 341
Figure 5-10. Single Frequency FM Function ..... 343
Figure 5-11. Sine Function ..... 344
Figure 5-12. 1st Sine Function Example ..... 345
Figure 5-13. 2nd Sine Function Example ..... 345
Figure 5-14. Trapezoidal Pulse with Bit Pattern ..... 347
Figure 5-15. Exponential Pulse with Bit Pattern ..... 349
Figure 6-1. Comparator Macromodel ..... 381
Figure 6-2. Op-amp (Linear) Macromodel ..... 384
Figure 6-3. Op-amp (Linear) Model Characteristics ..... 385
Figure 6-4. Op-amp (Linear 1-pole) Macromodel ..... 387
Figure 6-5. Op-amp (Linear 1-pole) Model Characteristics ..... 388
Figure 6-6. Op-amp (Linear 1-pole) Application Area ..... 390
Figure 6-7. Op-amp (Linear 1-pole) Frequency Response ..... 390
Figure 6-8. Op-amp (Linear 2-pole) Macromodel ..... 391
Figure 6-9. Op-amp (Linear 2-pole) Model Characteristic ..... 392
Figure 6-10. Delay Macromodel ..... 394
Figure 6-11. Saturating Resistor Macromodel ..... 395
Figure 6-12. Saturating Resistor Model Characteristics ..... 396
Figure 6-13. Voltage Limiter Macromodel ..... 397
Figure 6-14. Voltage Limiter Model Characteristics ..... 398
Figure 6-15. Current Limiter Macromodel ..... 399
Figure 6-16. Current Limiter Model Characteristics ..... 400
Figure 6-17. Voltage Controlled Switch Macromodel ..... 401
Figure 6-18. Current Controlled Switch Macromodel ..... 404
Figure 6-19. Ideal Single-Pole Multiple-Throw Switch Macromodel ..... 407
Figure 6-20. Triangular to Sine Wave Converter Macromodel ..... 409
Figure 6-21. Staircase Waveform Generator Macromodel ..... 411
Figure 6-22. Staircase Waveform Generator Model Characteristics ..... 412
Figure 6-23. Sawtooth Waveform Generator Macromodel ..... 413
Figure 6-24. Sawtooth Waveform Generator Model Characteristics ..... 414
Figure 6-25. Triangular Waveform Generator Macromodel ..... 415
Figure 6-26. Triangular Waveform Generator Model Characteristics. ..... 416
Figure 6-27. Amplitude Modulator Macromodel ..... 417
Figure 6-28. Pulse Amplitude Modulator Macromodel ..... 419
Figure 6-29. Sample \& Hold Macromodel ..... 421
Figure 6-30. Sample \& Hold Model Characteristics ..... 422
Figure 6-31. Track \& Hold Macromodel ..... 423
Figure 6-32. Track \& Hold Model Characteristics ..... 424
Figure 6-33. Pulse Width Modulator Macromodel ..... 425
Figure 6-34. Pulse Width Modulator Model Characteristics ..... 426
Figure 6-35. Pulse Width Modulator Duty Cycle ..... 427
Figure 6-36. Voltage Controlled Oscillator Macromodel ..... 428
Figure 6-37. Peak Detector Macromodel ..... 430
Figure 6-38. Peak Detector Simulation Results ..... 432
Figure 6-39. Level Detector Macromodel ..... 433
Figure 6-40. Logarithmic Amplifier Macromodel ..... 436
Figure 6-41. Anti-logarithmic Amplifier Macromodel ..... 438
Figure 6-42. Differentiator Macromodel ..... 440
Figure 6-43. Integrator Macromodel ..... 442
Figure 6-44. Adder, Subtractor, Multiplier \& Divider Macromodels ..... 444
Figure 7-1. Digital Model Parameter Thresholds ..... 450
Figure 7-2. Delay Macromodel ..... 453
Figure 7-3. Inverter Macromodel ..... 454
Figure 7-4. Analog to Digital Converter Macromodel ..... 463
Figure 7-5. Digital to Analog Converter Macromodel ..... 465
Figure 8-1. Transformer Winding Macromodel ..... 468
Figure 8-2. Non-linear Magnetic Core 1 Macromodel ..... 470
Figure 8-3. Symmetric B-H loops with Different Amplitudes ..... 472
Figure 8-4. Asymmetric Minor Loops ..... 472
Figure 8-5. Non-linear Magnetic Core 2 Macromodel ..... 473
Figure 8-6. Symmetric B-H loops with Different Amplitudes ..... 475
Figure 8-7. Asymmetric Minor Loops ..... 475
Figure 8-8. Linear Magnetic Core Macromodel ..... 476
Figure 8-9. Magnetic Air Gap Macromodel ..... 477
Figure 8-10. Transformer (Variable \# of Windings) Macromodel ..... 478
Figure 8-11. Ideal Transformer Macromodel ..... 480
Figure 9-1. Operational Amplifier Macromodel ..... 483
Figure 9-2. Cascaded Amplifier Macromodel ..... 485
Figure 9-3. Equivalent Circuit (Single-stage Amplifier) ..... 485
Figure 9-4. Equivalent Circuit (Two-stage Amplifier) ..... 486
Figure 9-5. Switch Macromodel ..... 488
Figure 9-6. Closed Switch Equivalent Circuit ..... 489
Figure 9-7. Open Switch Equivalent Circuit ..... 489
Figure 9-8. NMOS Switch ..... 489
Figure 9-9. PMOS Switch ..... 490
Figure 9-10. Ideal Operational Amplifier Macromodel ..... 492
Figure 9-11. SC Integrators \& LDI's ..... 493
Figure 9-12. Inverting Switched Capacitor Macromodel ..... 495
Figure 9-13. Non-inverting Switched Capacitor Macromodel ..... 498
Figure 9-14. Parallel Switched Capacitor Macromodel ..... 501
Figure 9-15. Serial Switched Capacitor ..... 503
Figure 9-16. Serial-parallel Switched Capacitor Macromodel ..... 505
Figure 9-17. Bi-linear Switched Capacitor Macromodel ..... 508
Figure 9-18. Unswitched Capacitor Macromodel ..... 510
Figure 9-19. Non-inverting Integrator ..... 513
Figure 9-20. LDI Phase Control Non-inverting Integrator Macromodel ..... 514
Figure 9-21. Euler Forward Integrator Macromodel ..... 515
Figure 9-22. LDI Phase Control Euler Forward Integrator Macromodel ..... 516
Figure 9-23. Euler Backward Integrator Macromodel ..... 517
Figure 9-24. LDI Phase Control Euler Backward Integrator Macromodel ..... 518
Figure 10-1. Piece Wise Linear Example 1 ..... 568
Figure 10-2. Piece Wise Linear Example 2 ..... 568
Figure 10-3. PWL, PWL_CTE and PWL_LIN Functions ..... 609
Figure 10-4. TPD Example ..... 655
Figure 10-5. Smith chart plot using STOSMITH/ZTOSMITH/YTOSMITH functions ..... 826
Figure 10-6. Example Test Vector File ..... 919
Figure 10-7. Test Vector Output Evaluation ..... 923
Figure 11-1. OPSELDO_JWDB_RUN option effect ..... 1009
Figure 12-1. Circuit Components with their Added Noise Sources ..... 1024
Figure 12-2. High-rate Particle Detector Circuit ..... 1026
Figure 12-3. Simulation Results—Input \& Output Signals ..... 1027
Figure 12-4. Noise at Amplifier O/P ..... 1028
Figure 12-5. Noise at Analog Memory O/P ..... 1029
Figure 12-6. Switched Capacitor Filter Circuit Schematic ..... 1031
Figure 12-7. Amplifier Schematic ..... 1032
Figure 12-8. AC \& Noise Simulation Results of Amplifier ..... 1033
Figure 12-9. AC \& Noise Simulation of Amplifier Macromodel ..... 1034
Figure 12-10. Simulation Results of the Filter ..... 1037
Figure 12-11. Frequency Response of the Filter ..... 1038
Figure 16-1. Example 1-bjtinv ..... 1105
Figure 16-2. Example 2-ivdd ..... 1108
Figure 16-3. Example 3-oscil ..... 1112
Figure 16-4. Example 4-moy1 ..... 1114
Figure 16-5. Example 5-ladder ..... 1116
Figure 16-6. Example 6-opamp_5pin ..... 1119
Figure 18-1. Discretization of final parameters ..... 1146
Figure 18-2. Values of the merit function ..... 1156
Figure 18-3. Response of the filter ..... 1157
Figure 18-4. Optimized response (starting from a different point) ..... 1159
Figure 18-5. Illustration of I-V characteristics ..... 1160
Figure 18-6. Simulator as black box ..... 1166
Figure 18-7. Discretization of design parameters ..... 1168
Figure 18-8. Effect of the OPSELDO_OUTER option ..... 1170
Figure 18-9. Examples of non smooth problems ..... 1175
Figure 18-10. Different types of minima ..... 1176
Figure 18-11. Illustration of the optimality conditions ..... 1187
Figure 18-12. Illustration of the constraints $c_{1}{ }^{(i)} \leq c^{(i)}(\mathrm{x}) \leq \mathrm{c}_{\mathrm{u}}{ }^{(\mathrm{i})}$ ..... 1188
Figure 18-13. Non-valid and valid zeros ..... 1190
Figure 18-14. Illustration of the 'elastic' mode (1) ..... 1201
Figure 18-15. Illustration of the 'elastic' mode (2) ..... 1203
Figure 19-1. Monte Carlo Analysis Example ..... 1222
Figure 20-1. Cuboidal representation of two 3-factors designs ..... 1231
Figure 20-2. Common statistics for UNIF(,) ..... 1248
Figure 20-3. Percentage of cases in eight portions of the Gaussian distribution ..... 1250
Figure 20-4. Factor levels $\mathrm{x}_{\text {low }}$ and $\mathrm{x}_{\text {high }}$ for a circuit parameter x ..... 1251
Figure 23-1. Input Buffer Model Building Blocks ..... 1290
Figure 23-2. Terminator Buffer Model Building Blocks ..... 1291
Figure 23-3. Output Buffer Model Building Blocks ..... 1292
Figure 23-4. I/O Buffer Model Building Blocks ..... 1293
Figure 23-5. 3_state Buffer Model Building Blocks ..... 1294
Figure 23-6. A Pseudo-Differential Input Buffer Consisting of two Single-Ended Input Buffers 1295
Figure 23-7. A Pseudo-Differential Output Buffer Consisting of two Single-Ended Output Buffers ..... 1295
Figure 23-8. An Analog-Only Model init using an I/O Buffer as an Example ..... 1296
Figure 23-9. Simple Passive Modeling ..... 1297
Figure 23-10. Series Current Modeling ..... 1297
Figure 23-11. Series MOSFET Modeling ..... 1297
Figure 23-12. Each Pin is Assumed to have Parasitic Resistance R_pkg, Inductance L_pkg, and Capacitance C_pkg ..... 1298
Figure 23-13. [Pin Mapping] Contains Information about Bus Connection from Buffer Nodes to Supply/ Ground Nodes ..... 1299
Figure 23-14. Series Elements can be Connected Between Buffer Die Pads using the [Series Pin Mapping] Keyword ..... 1300
Figure 23-15. Test_component Example ..... 1318
Figure 23-16. Package model example ..... 1321
Figure 23-17. Single-Ended Tx-Rx System ..... 1330
Figure 23-18. Single-Ended Tx-Rx System Simulation Results ..... 1332
Figure 23-19. Pseudo-Differential Tx-Rx System Simulation Results ..... 1335
Figure 23-20. Package Parasitics Cross Talk. ..... 1337
Figure 23-21. Component Internal Connection ..... 1338
Figure 23-22. Simultaneous Switching Output Noise (SSON) Simulation Results ..... 1340
Figure 24-1. Parallel LCR Circuit ..... 1342
Figure 24-2. Tutorial \#1—Simulation Results ..... 1344
Figure 24-3. 4th Order Butterworth Filter ..... 1345
Figure 24-4. Tutorial \#2-Simulation Results-1 ..... 1347
Figure 24-5. Tutorial \#2-Simulation Results-2 ..... 1348
Figure 24-6. Band Pass Filter. ..... 1349
Figure 24-7. Tutorial \#3-Simulation Results ..... 1352
Figure 24-8. Low Pass Filter ..... 1353
Figure 24-9. Tutorial \#4-Simulation Results ..... 1355
Figure 24-10. Colpitts Oscillator ..... 1356
Figure 24-11. Tutorial \#5-Simulation Results ..... 1358
Figure 24-12. High Voltage Cascade ..... 1359
Figure 24-13. Tutorial \#6-Simulation Results-1 ..... 1361
Figure 24-14. Tutorial \#6-Simulation Results-2 ..... 1362
Figure 24-15. Non-inverting Amplifier ..... 1363
Figure 24-16. Tutorial \#7-Simulation Results ..... 1365
Figure 24-17. Bipolar Amplifier ..... 1366
Figure 24-18. Tutorial \#8—Simulation Results ..... 1368
Figure 24-19. Tutorial \#9—Simulation Results-1 ..... 1370
Figure 24-20. Tutorial \#9-Simulation Results-2 ..... 1371
Figure C-1. Example\#1—Simulation Results ..... 1461
Figure C-2. Example\#2-Simulation Results-1 ..... 1464
Figure C-3. Example\#2-Simulation Results-2 ..... 1465
Figure C-4. Example\#3-Simulation Results ..... 1467
Figure C-5. Example\#4—Simulation Results ..... 1469
Figure C-6. Example\#5-Simulation Results ..... 1472
Figure C-7. Example\#6-Simulation Results ..... 1474
Figure C-8. Example\#7-Simulation Results ..... 1477
Figure C-9. Example\#8-Simulation Results ..... 1480
Figure C-10. Example\#9—Simulation Results-1 ..... 1481
Figure C-11. Example\#9—Simulation Results-2 (Zoom) ..... 1482
Figure F-1. IP Protection ..... 1502

## List of Tables

Table 1-1. Documentation Conventions ..... 38
Table 3-1. Scale Factors ..... 73
Table 3-2. Arithmetic Functions and Operators ..... 78
Table 3-3. Operator Precedence ..... 82
Table 3-4. Boolean Operators ..... 83
Table 3-5. Bitwise Operators ..... 84
Table 4-1. Eldo Device Models ..... 119
Table 4-2. Resistor Model—Level 1 Parameters ..... 128
Table 4-3. Resistor Model—Level 2 Parameters ..... 131
Table 4-4. Resistor Model-Level 4 Parameters ..... 131
Table 4-5. Capacitor Model Parameters ..... 137
Table 4-6. Inductor Model Parameters ..... 145
Table 4-7. RC Wire Model Parameters ..... 150
Table 4-8. Diffusion Resistor Model Parameters ..... 154
Table 4-9. Semiconductor Resistor Model Parameters ..... 157
Table 4-10. LDTL Level 3 Parameter Combinations ..... 175
Table 4-11. RLGC Separator Characters ..... 185
Table 4-12. Lossy Transmission Line: U Model Parameter Combinations ..... 196
Table 4-13. Microstrip T Junction Parameters ..... 198
Table 4-14. Microstrip Bend (Arbitrary Angle, Optimally Mitered) Parameters ..... 201
Table 4-15. 90-degree Microstrip Bend (Mitered) Parameters ..... 204
Table 4-16. 90-degree Microstrip Bend (Optimally Mitered) Parameters ..... 207
Table 4-17. 90-degree Microstrip Bend (Unmitered) Parameters ..... 210
Table 4-18. Microstrip Step in Width Parameters ..... 213
Table 4-19. Cylindrical Via Hole in Microstrip Parameters ..... 215
Table 4-20. Unmitered Stripline Bend Parameters ..... 218
Table 4-21. Stripline T Junction Parameters ..... 221
Table 4-22. Stripline Step in Width Parameters ..... 223
Table 4-23. Diode Models ..... 228
Table 4-24. Diode Models with -compat ..... 229
Table 4-25. BJT Models ..... 235
Table 4-26. BJT Models with -compat ..... 236
Table 4-27. VBIC Version Selection ..... 239
Table 4-28. HICUM version selection ..... 240
Table 4-29. HICUM/Level0 version selection ..... 242
Table 4-30. JFET Models ..... 246
Table 4-31. MESFET Models ..... 248
Table 4-32. MOSFET Models ..... 253
Table 4-33. MOS Levels with -compat ..... 255
Table 4-34. MOS Noise Models ..... 256
Table 4-35. MOS Noise Models ..... 256
Table 4-36. MOSFET Common Parameters ..... 259
Table 4-37. RLEV Default Values ..... 263
Table 4-38. ALEV Default Values ..... 263
Table 4-39. DIOLEV Default Values ..... 263
Table 4-40. DCAPLEV Default Values ..... 264
Table 4-41. Merckel-Spice ..... 267
Table 4-42. EKV MOS Models ..... 271
Table 4-43. BSIM3v3 Models ..... 273
Table 4-44. Berkeley BSIM3v3 States ..... 276
Table 4-45. BSIMSOI3 Version Selection ..... 280
Table 4-46. SOIMOD Selection ..... 280
Table 4-47. Philips MOS9 Version Selection ..... 284
Table 4-48. Berkeley BSIM4 Version Selection ..... 285
Table 4-49. Philips MOS Model 11 Version Selection ..... 287
Table 4-50. HiSIM Version Selection ..... 289
Table 4-51. PSP Version Selection ..... 291
Table 4-52. BSIMSOI4 Version Selection ..... 293
Table 4-53. HiSIM-LDMOS Version Selection ..... 294
Table 4-54. MOSVAR Version Selection ..... 294
Table 6-1. Comparator Parameters ..... 382
Table 6-2. Op-amp (Linear) Model Parameters ..... 384
Table 6-3. Op-amp (Linear 1-pole) Model Parameters ..... 387
Table 6-4. Op-amp (Linear 2-pole) Model Parameters ..... 391
Table 6-5. Saturating Resistor Model Parameters ..... 395
Table 6-6. Voltage Limiter Model Parameters ..... 397
Table 6-7. Current Limiter Model Parameters ..... 399
Table 6-8. Voltage Controlled Switch Model Parameters ..... 401
Table 6-9. Current Controlled Switch Model Parameters ..... 404
Table 6-10. Ideal Single-Pole Multiple-Throw Switch Parameters ..... 407
Table 6-11. Triangular to Sine Wave Converter Model Parameters ..... 409
Table 6-12. Staircase Waveform Generator Model Parameters ..... 411
Table 6-13. Sawtooth Waveform Generator Model Parameters ..... 413
Table 6-14. Triangular Waveform Generator Model Parameters ..... 415
Table 6-15. Amplitude Modulator Model Parameters ..... 417
Table 6-16. Pulse Amplitude Modulator Model Parameters ..... 419
Table 6-17. Sample \& Hold Model Parameters ..... 421
Table 6-18. Track \& Hold Model Parameters ..... 423
Table 6-19. Pulse Width Modulator Model Parameters ..... 425
Table 6-20. Voltage Controlled Oscillator Model Parameters ..... 428
Table 6-21. Peak Detector Model Parameters ..... 430
Table 6-22. Level Detector Model Parameters ..... 433
Table 6-23. Logarithmic Amplifier Model Parameters ..... 436
Table 6-24. Anti-logarithmic Amplifier Model Parameters ..... 438
Table 6-25. Differentiator Model Parameters ..... 440
Table 6-26. Integrator Model Parameters ..... 442
Table 6-27. Adder, Subtractor, Multiplier \& Divider Model Parameters ..... 444
Table 7-1. 2-Input Digital Gate Types ..... 457
Table 7-2. 3-Input Digital Gate Types ..... 459
Table 7-3. Multiple Input Digital Gate Types ..... 461
Table 8-1. Transformer Winding Model Parameters ..... 468
Table 8-2. Non-linear Magnetic Core 1 Model Parameters ..... 470
Table 8-3. Non-linear Magnetic Core 2 ..... 473
Table 8-4. Linear Magnetic Core Model Parameters ..... 476
Table 8-5. Magnetic Air Gap Model Parameters ..... 477
Table 8-6. Transformer Model Parameters ..... 478
Table 9-1. Operational Amplifier Model Parameters ..... 487
Table 9-2. Switch Model Parameters ..... 490
Table 9-3. Inverting Switched Capacitor Model Parameters ..... 496
Table 9-4. Non-inverting Switched Capacitor Model Parameters ..... 498
Table 9-5. Parallel Switched Capacitor ..... 501
Table 9-6. Serial Switched Capacitor Model Parameters ..... 503
Table 9-7. Serial-parallel Switched Capacitor Model Parameters ..... 506
Table 9-8. Bi-linear Switched Capacitor Model Parameters ..... 508
Table 9-9. Unswitched Capacitor Model Parameters ..... 510
Table 10-1. Eldo Analysis Commands ..... 519
Table 10-2. Eldo Display Commands ..... 521
Table 10-3. Eldo Simulation Control Commands ..... 522
Table 10-4. Eldo Circuit Description Commands ..... 524
Table 10-5. .A2D - Global Parameters ..... 529
Table 10-6. Option D2DMVL9BIT effect ..... 537
Table 10-7. Wildcard Characters ..... 555
Table 10-8. .D2A Global Parameters ..... 577
Table 10-9. PWL Function Types ..... 605
Table 10-10. Monte Carlo Extract Outputs ..... 642
Table 10-11. Extract Function Parameters ..... 643
Table 10-12. Transient Extraction Language Functions ..... 645
Table 10-13. General Extraction Language Functions ..... 646
Table 10-14. XYCOND Arithmetic Expressions ..... 660
Table 10-15. LSTB Output Formats ..... 703
Table 10-16. Model Types ..... 723
Table 10-17. Operating Point-optyp values ..... 757
Table 10-18. Operating Point-optyp values Dynamic Part for Charge Control Model ..... 759
Table 10-19. Spice3e Capacitance / Eldo Capacitance ..... 759
Table 10-20. Default Values for Time Window Parameters ..... 764
Table 10-21. Reserved Keywords Never Available in .PARAM ..... 779
Table 10-22. Reserved Keywords Not Available in .PARAM if an RF Analysis is Specified in the Netlist ..... 779
Table 10-23. Two-port Parameter Keywords ..... 798
Table 10-24. MOSFET Plotting and Printing ..... 802
Table 10-25. BJT Plotting and Printing ..... 806
Table 10-26. JFET Plotting and Printing ..... 808
Table 10-27. Diode Plotting and Printing ..... 809
Table 10-28. Common Plotting and Printing ..... 809
Table 10-29. Element Output ..... 814
Table 10-30. Two-port Parameters ..... 818
Table 10-31. Special Characters ..... 844
Table 10-32. Test Vector Radix Values ..... 921
Table 10-33. Test Vector State Characters ..... 922
Table 11-1. Eldo Options ..... 940
Table 11-2. Simulator Compatibility Options ..... 944
Table 11-3. Netlist Parser Control Options ..... 944
Table 11-4. Simulation Speed, Accuracy and Efficiency Options ..... 945
Table 11-5. Miscellaneous Simulation Control Options ..... 945
Table 11-6. Model Control Options ..... 946
Table 11-7. RC Reduction Options ..... 946
Table 11-8. Noise Analysis Options ..... 946
Table 11-9. Simulation Display Control Options ..... 947
Table 11-10. Simulation Output Control Options ..... 947
Table 11-11. Optimizer Output Control Options ..... 948
Table 11-12. File Generation Options ..... 948
Table 11-13. Mathematical Algorithm Options ..... 948
Table 11-14. Mixed-Mode Options ..... 948
Table 11-15. Other Options ..... 949
Table 13-1. Default Rule ..... 1043
Table 14-1. Global Tuning of Accuracy ..... 1071
Table 16-1. IEM Supported MOS Models ..... 1099
Table 16-2. IEM Supported BJT Models ..... 1100
Table 16-3. IEM Supported Diode Models ..... 1100
Table 18-1. Nomenclature ..... 1128
Table 18-2. .OBJECTIVE Restrictions ..... 1137
Table 18-3. Basic Examples of Circuit Optimization ..... 1149
Table 18-4. Results of Optimization for GOAL Objectives ..... 1152
Table 18-5. Results of Optimization for MINIMIZE Objectives ..... 1153
Table 18-6. Extracted Information from .otm File ..... 1154
Table 18-7. Combinations of N1 and LS Values ..... 1154
Table 18-8. Results of Restricted Problem ..... 1155
Table 18-9. Values Extracted from fourband.otm File ..... 1158
Table 18-10. Values Extracted from nmos.otm File ..... 1161
Table 18-11. Optimization Result Status Code ..... 1198
Table 21-1. Eldo Reliability Commands ..... 1253
Table 22-1. C and PPL Syntax ..... 1257
Table 22-2. Built-In Waveform Functions ..... 1261
Table 22-3. Built-In DSP Functions ..... 1272
Table 23-1. List of Predefined Port Names and their Descriptions ..... 1288
Table 23-2. Buffer Types and Port Names Used ..... 1289
Table 23-3. Digital Port Logic Levels ..... 1301
Table 23-4. Analog Levels ..... 1301
Table 23-5. Exceptions to Fast=Max, Slow=Min Rule ..... 1305
Table 23-6. Supported Keywords and Sub-Parameters ..... 1324
Table 24-1. Tutorials ..... 1341
Table 25-1. MOS Levels with -compat ..... 1374
Table 25-2. BJT Models with -compat ..... 1375
Table 25-3. Diode Models with -compat ..... 1375
Table 25-4. Resistor Level with -compat ..... 1375
Table 25-5. MOS Levels in TIspice Compatibility Mode ..... 1384
Table 25-6. BJT Models in TIspice Compatibility Mode ..... 1384
Table 25-7. Supported Keywords for Voltage on a Device ..... 1388
Table 25-8. Spectre Constants and Functions ..... 1398
Table 25-9. Spectre Conversion Error Messages ..... 1401
Table A-1. Global Errors ..... 1412
Table A-2. Errors Related to Nodes ..... 1415
Table A-3. Errors Related to Objects ..... 1416
Table A-4. Errors Related to Commands ..... 1423
Table A-5. Errors Related to Models ..... 1430
Table A-6. Errors Related to AMODELS ..... 1431
Table A-7. Errors Related to Subcircuits ..... 1432
Table A-8. Miscellaneous Errors ..... 1432
Table A-9. Global Warnings ..... 1436
Table A-10. Warnings Related to Nodes ..... 1439
Table A-11. Warnings Related to Objects ..... 1440
Table A-12. Warnings Related to Commands ..... 1443
Table A-13. Warnings Related to Models ..... 1448
Table A-14. Warnings Related to Subcircuits ..... 1450
Table A-15. Miscellaneous Warnings ..... 1450
Table A-16. Miscellaneous Warnings ..... 1451
Table C-1. Eldo Examples ..... 1459
Table E-1. ffcv Output Format Modifier ..... 1497
Table G-1. Eldo/Eldo-ST Model Levels ..... 1509
Table G-2. STMicroelectronics Model Selection ..... 1510
Table G-3. STMicroelectronics Junction Diode Model Selection ..... 1510
Table G-4. STMicroelectronics MOSFET Model Selection ..... 1511
Table G-5. STMicroelectronics BJT Model Selection ..... 1511

## Chapter 1 Introduction to Eldo

## Introduction

The Eldo ${ }^{\circledR}$ analog simulator is the core component of a comprehensive suite of analog and mixed-signal simulation tools. Eldo offers a unique partitioning scheme allowing the use of different algorithms on differing portions of design. It allows the user a flexible control of simulation accuracy using a wide range of device model libraries, and gives a high accuracy yield in combination with high speed and high performance.

## Overview

The following is a list of the major product features of Eldo:

- Eldo is the core technology allowing to address RF simulation (Eldo RF) and mixedsignal (Questa ADMS, ADMS-ADiT)
- Simulation of very large circuits (up to around 300,000 transistors) in time and frequency domains
- $3 \times$ to $10 \times$ gain in simulation speed over other commercial SPICE simulators, while maintaining same accuracy
- Three complementary transient simulation algorithms (OSR, Newton, IEM)
- Flexible user control of simulation accuracy
- Unique transient noise algorithm
- Advanced analysis options such as pole-zero, enhanced Monte Carlo, DC mismatch
- Circuit optimization and statistical analysis (Design of Experiments)
- S and Z-domain generalized transfer functions
- Reliability simulation (Eldo UDRM)
- Flexible DSPF netlist support
- Behavioral modeling with Verilog-A
- Extensive device model libraries including leading MOS, bipolar and MESFET transistor models such as the BSIM3v3.x, BSIM 4, MM11, Mextram, HICUM, and PSP
- TSMC Model Interface (TMI) support
- IBIS (I/O Buffer Information Specification) model support
- Integration into Mentor Graphics IC flow, consisting of Design Architect IC for schematic capture, IC station for the layout side, and Calibre/Calibre xRC for DRC/LVS and extraction. This flow provides a complete, front-to-back design and verification environment for analog, mixed-signal and RF.
- Integration into Cadence's Analog Artist environment (Artist Link)


## Eldo Input and Output Files

The following flowchart shows the input files that must be provided for an Eldo simulation run and the output files that Eldo produces:

Figure 1-1. Eldo Input \& Output Files


Figure 1-1 shows the main files used by Eldo. A brief description of each is given below:
<file>.cir The main Eldo control file, containing circuit netlist, stimulus and simulation control commands. This file is SPICE compatible, the Eldo control language being a superset of the Berkeley SPICE syntax.
<file>.chi SPICE compatible output log file containing ASCII data, including results and error messages.
<file>.wdb A binary output file for mixed-signal JWDB format files. This is always generated by default. Viewed with the EZwave waveform viewer. By default, using the.$w d b$ format, the . Extract and .meas waveforms are also saved inside the $E X T$ folder in the main . $w d b$ file. Waveforms defined by .DEFWAVE commands combined with . Plot are saved inside the appropriate analysis folder (for example TRAN) in the main .wdb file.
<file>.swd A saved windows file used by the EZwave waveform viewer. This file contains information on waveforms and their display and cursor settings, window format settings and complex waveform transition settings.

Other files not generated by default and not shown in the figure are:
<file>.cou A binary output file containing Eldo analog simulation results data. A special interface is provided to access this data from your own post-processor software if required. This is a legacy output format. Please refer to the Eldo cou Library User's Manual for more details.
<file>.ext A file containing extraction or waveform information, created when using a . EXtract command in the netlist and the .cou format output is specified. This file will not always be output, it depends on the type of simulation and the specification of the .EXTRACT command.
$<$ file>.ext.wdb
A file containing extraction or waveform information, created when using a .extract command in the netlist with option extfile specified (using the default .wdb format). This file will not always be output, it depends on the type of simulation and the specification of the .EXTRACT command.
<file>.meas A file containing extraction or waveform information when the commands .EXTRACT, . MEAS, or . РLot $\mathbf{W}(\mathrm{XX})$ are present in an input netlist and the .cou format output is specified. This file will not always be output, it depends on the type of simulation and the specification of the .EXTRACT, .meas, or . PLOT W(XX) command.
$\langle f i l e>. m e a s . w d b$
A file containing extraction or waveform information when the commands .EXTRACT, . MEAS, or . РLOT $\mathrm{W}(\mathrm{XX})$ are present in an input netlist with option measfile specified (using the default. $w d b$ format). This file will not always be output, it depends on the type of simulation and the specification of the .EXTRACT, .MEAS, or .PLOT $\mathbf{W}(\mathrm{XX})$ command.

## Note

The above four types of file (.ext, .ext.wdb, .meas, .meas.wdb) are also generated when functions are used in .Defwave commands. In most cases, the result of such functions are known only at the end of the simulation, so the waves issued from a . Defwave can not be plotted in the .cou output file, but only in a specific file generated at the end of the simulation. These types of file are not generated if you don't use .PLot or .PRINT commands in the netlist or options extfile or measfile specified.
<file>.aex A file containing extraction information, created when . OPtion aex is used in conjunction with . EXTRACT or .meAS commands.
<file>.pz The output file used by the Pole Zero post-processor.
<file>.spi3 SPICE3 compatible output file.
<file>.wsf Cadence compatible output file.
<file>.fsdb nWave viewer compatible output file.
The .cou, .ext, .meas, .aex, .pz, .spi3, .wsf, and.$f s d b$ files are only produced by Eldo when the user has set appropriate options in the input file or command line flags.

For more details, refer to Simulator Commands.

## Getting Started

## How to Run Eldo

To run an Eldo simulation, a .cir control file must be supplied to the simulator. As can be seen in the previous example, this file must include the following:

- Circuit connectivity, i.e. a netlist.
- Model parameter values defining the specific device models to be used.
- Electrical stimuli (sources).
- Simulation options and commands.

Input and output formats are compatible with Berkeley SPICE 2G6, however Eldo provides additional features not implemented in SPICE.

## Schematic Example

This example consists of a simple cascade of three inverters. The figures below show the circuit diagram for the cascade together with the inverter subcircuit. In order to create the Eldo netlist, node names must be assigned to the circuit. The complete netlist is shown on the following page.

Figure 1-2. Cascaded Inverter Circuit


Figure 1-3. Inverter Subcircuit


## Associated Netlist

The .cir control file for Eldo can be generated using a basic text editor, or alternatively a schematic editor that is capable of generating SPICE-like format.

For further information, please refer to Eldo Control Language.

## Sample circuit .cir control file

```
* MOS model definitions
.model m1 nmos level=3 vto=1v uo=550 vmax=2.0e5
+ cgdo=0.4p cgbo=2.0e-10 cgso=4.0e-11 cjsw=10.e-9
+ mjsw=0.3 tox=1.0e-7 nsub=1.0e16 nfs=1.5e10
+ xj=0.5u ld=0.5u pb=0.75 delta=0.9 eta=0.95
+ kappa=0.45 gamma=0.37
.model p1 pmos level=3 vto=-1v uo=230 vmax=1.9e5
+ cgdo=0.4p cgbo=2.0e-10 cgso=4.0e-11 cjsw=10.e-9
+ mjsw=0.3 tox=1.0e-7 nsub=1.0e16 nfs=1.5e10
+ xj=0.5u ld=0.5u pb=0.75 delta=0.9 eta=0.95
+ kappa=0.45 gamma=0.37
* Subcircuit definition
.subckt inv 1 2 3
m2 2 1 0 0 m1 w=10u l=4u ad=100p pd=40u as=100p
m1 2 1 3 3 pl w=15u l=4u ad=100p pd=40u as=100p
c1 2 0 0.5p
.ends inv
* Subcircuit calls
x1 1 2 6 inv
x2 2 3 6 inv
x3 3 4 6 inv
cload 4 0 1p
* Electrical source definitions
vdd 6 0 5v
vin 1 0 pulse(0 5 10e-9 5e-9 5e-9 30e-9 50e-9)
* Simulation options & commands
.tran 0.5n 100n uic
.ic v(1)=0
.plot tran v(1) v(2) v(3) v(4)
.print tran v(1) v(2) v(3) v(4)
.option eps=0.5e-3 tnom=50 list node
.end
```

Please see "Documentation Conventions" on page 38 for a detailed description on the meanings of the different fonts, brackets, and so on, used throughout this manual.

## Running a Simulation

To run a simulation from the command line (see "Running Eldo" on page 41 for a full list of options) use the following command:
eldo cir_file_name.cir

After the simulation has been completed, Eldo writes simulator information to the .chi file. This file will contain details of the simulation including any warning or error messages, which may have been encountered during simulation. A binary . $w d b$ file is also generated by default as an output of simulation. The user can view the results written to the.$w d b$ file, with the EZwave viewer. The.$w d b$ file can be opened in the EZwave viewer the using the following command:
ezwave cir_file_name.wdb

For further information regarding the use of EZwave, please refer to the EZwave User's Manual.

See Figure 1-4 for an example binary output file (.wdb) viewed with EZwave.
Figure 1-4. EZwave output (.wdb)


## Related Documentation

Other documents and manuals that are referenced in this manual, and that you may need to refer to are:

- Eldo Device Equations Manual for a complete set of Eldo model equations
- Eldo RF User's Manual
- Eldo UDM User's Manual
- Eldo UDRM User's Manual
- Eldo Verilog-A User's Manual
- EZwave User's and Reference Manual
- Questa ADMS User's Manual
- ADiT User's Manual
- CFAS User's Manual
- Eldo cou Library User's Manual


## Documentation Conventions

The following is a list of documentation conventions used throughout the Eldo User's Manual both in the syntax and in the syntax descriptions:

Table 1-1. Documentation Conventions

| USER INPUT | Eldo netlist content is always shown in courier non-bold typeface. Eldo is <br> case insensitive. |
| :--- | :--- |
| KEYWORDS | Eldo keywords are shown in courier bold typeface. Eldo is case <br> insensitive. <br> Example: nONOISE is an Eldo keyword. |
| [ ] | Square brackets indicate that a parameter is optional. Optional parameter <br> declarations may also be nested. <br> Example: [ [DC] DCVAL] shows that the value parameter DCVAL is optional <br> with the possibility of specifying another optional keyword parameter DC. |
| \{ \} | Braces (curly brackets) indicate multiple occurrences of a parameter. <br> Example: NN \{NN\} shows that the parameter NN may be specified more than <br> once. The parameter NN could be a node name for example. |

## Table 1-1. Documentation Conventions

| \{ \} | Certain syntax, for example expressions, have to be enclosed in braces (curly brackets). In these cases, the braces are shown in bold in order to distinguish them from the braces used above to indicate multiple occurrences. They are part of the syntax. <br> Example: VALUE $=\{2 \mathrm{U} * \mathrm{~V}(3,4) * I(\mathrm{~V} 5)\}$ shows that value is calculated by the expression in braces. |
| :---: | :---: |
| ( ) | Certain syntax, for example pairs of values or functions, must be specified inside brackets, often with a comma to separate values from one another. They are shown in boLd to avoid confusion with other parentheses. They are part of the syntax. <br> Example: PULSE (V0 V1 [TD [TR [TF [PW [PER]]]]]) shows the parameter specifications for a pulse function with bold brackets () to indicate that all the parameters must be enclosed in brackets. |
| , | A comma is used to separate pairs of values. It is shown in bold in order to indicate that it is actually part of the syntax which must be specified. <br> Example: $\left.\mathrm{I}\left(\mathrm{V} x x^{[ }, \mathrm{V}_{\mathrm{yy}}\right]\right)$ shows the syntax for obtaining the current difference between the voltage sources $\mathrm{v}_{\mathrm{xx}}$ and $\mathrm{v}_{\mathrm{yy}}$ within the .PRINT command. |
|  | Used to indicate the start of an Eldo command. All Eldo commands must begin with a dot since it is part of the command syntax. The dot is shown in bold as well as the command since it can be considered to be part of the command keyword. <br> Example: . MODEL MNAME TYPE [PAR=VAL] shows the syntax for a model declaration. |
| $\cdot$ | An unbold dot is used to indicate nodes or subcircuits within other subcircuits. Example: .plot $\mathrm{v}(\mathrm{x} 2 . \mathrm{x} 1.1)$ shows the plotting of node 1 which is inside subcircuit x1 which is inside subcircuit x2. |
| < > | Angle brackets are sometimes used to indicate items which are not part of the syntax, but which are descriptions, and so on. <br> Example: <br> ... <br> <CIRCUIT_COMPONENTS> <br> ... <br> The angle brackets are used to prevent the name CIRCUIT_COMPONENTS from being confused with the Eldo syntax. <CIRCUIT_COMPONENTS> above simply means that between the dots, ..., may be a number of different circuit components. |
| \| | The logical OR symbol is used to indicate that one of the parameters must be chosen. <br> Example: $\mathbf{r}\|\mathbf{c}\| \mathbf{I} \mid \mathbf{V}$ shows that either $\mathbf{R}, \mathbf{c}, \mathbf{I}$ or $\mathbf{v}$ must be chosen. |

The conventions described above are used in combination with each other to describe the way in which the syntax has to be specified.

Introduction to Eldo
Documentation Conventions

## Example

```
.SUBCKT NAME NN {NN} [(ANALOG)] [PARAM: PAR=VAL {PAR=VAL}]
<CIRCUIT_COMPONENTS>
    .ENDS [NAME]
    .SUBCKT LIB FNAME SNAME [LIBTYPE]
```

Shows the syntax for a subcircuit definition.

## Chapter 2 <br> Running Eldo

This chapter is divided into the following sections:

- "Running Eldo from the Command Line" on page 41
- "Viewing Eldo Documentation" on page 57
- "Multi-Threading Eldo Simulations" on page 58
- "Eldo Initialization File" on page 60
- "Location Maps" on page 61
- "Statistics File" on page 63


## Running Eldo from the Command Line

When invoking Eldo at the command line, the following command line flags can be used:

```
eldo cir_filename
[-32b] [-64b]
[-adit] [-aditbb]
[-ai veriloga_dir_name]
[-alter alter_name | alter_index]
[-ascii]
[-b]
[-checksyntax]
[-clean]
[-cntthread]
[-compat] [-compmod] [-compnet]
[-convert_iic src_file dest_file]
[-cou]
[-cou47]
[-couext]
[-createoutpath output_dir_name]
[-dbledefs]
[-dbp]
[-d -define macro]
[-E] [-EE]
[-eil file]
[-extract filename]
[-ezwave]
[-float]
[-gwl gwl_lib_name]
[-h hostname]
[-hdlpath veriloga_path]
[-help [commands|devices|sources|manual]]
[-i cir_filename]
```

```
[-inter]
[-isaving [val]]
[-jwdb_config swd_filename]
[-jwdb_extensions]
[-jwdb_nocomplex]
[-jwdb_norffolder]
[-jwdb_servermode]
[-jwdb_threshold [val]]
[-l log_filename]
[-lib object_library_dir_name]
[-libinc]
[-m subckt_name]
[-m53]
[-mgls_async]
[-mthread]
[-noascii]
[-nocatmx]
[-nochi]
[-noconf]
[-nocouext]
[-noerrmlog]
[-nogwl]
[-noinit]
[-nojwdb]
[-no_sst_mthread]
[-nostver]
[-o output_filename]
[-opseldo_jwdb_run]
[-out out_filename]
[-outname out_filename]
[-outpath output_dir_name]
[-ovstatus]
[-parse_only]
[-plspath dir_name]
[-probeop2]
[-queue]
[-restart ["[save_file] [file=wfile]"]]
[-ri]
[-savetime time]
[-searchpath path_list]
[-silent]
[-sp spectre_file [-i spice_command_file] [-s2emode 2|1] [-clean_sp]
    [-spectre_out pathname] [-sp_plot 2|1|0]]
[-spiout]
[-spmodel <subckt_name1> -spmodel <subckt_name2> ...]
[-ssh hostname]
[-ssim]
[-stat [-statfile filename]]
[-stver]
[-tuning [FAST|STANDARD|ACCURATE|VHIGH] -tuning [BACKANNOTATE]]
[-use_proc n | HALF | MAX k | ALL | HYPER]
[-useht]
[-usethread val]
[-v]
[-vamodel <mod_name1> -vamodel <mod_name2> ...]
[-verbose]
[-vlac]
[-wB cou_filename]
```

```
[-wdl_timeout time]
```

It is also possible to create a file named eldo.ini which will be interpreted and loaded at the very beginning of each simulation. "Loading eldo.ini" is displayed whenever a valid eldo.ini file is found. See "Eldo Initialization File" on page 60 for further details.

- cir_filename

Name of the .cir control file to be simulated. Default extension is .cir. By default, the first parameter in the command line is taken to be the cir_filename by default.

Caution
The cir_filename is mandatory. All other flags are optional.

The function of the command line flags is as follows:

- -32 b

Runs the simulation in 32-bit mode on a 64-bit machine. This could speed-up simulations that require small amounts of memory.

- -64 b

Runs the simulation in 64-bit mode (available for Solaris and Linux platforms that have had 64-bit OS installed). This enables simulation of circuits which would require more than 2GB of memory, and which would therefore not work on 32-bit machines.

To run Eldo with the -64 b flag on a Solaris 64-bit machine you must first set the environment variable $A M S \_V C O \_M O D E$ to 64 , for example:
setenv AMS_VCO_MODE 64

## Note

Only a subset of Eldo/Eldo RF is ported. The following features are not supported: SimPilot interface, HDL-A, and output file formats other than .coul.wdb file.

- -adit

Sends blocks to ADiT instead of Eldo. Can be overridden by the netlist partitioning commands. Once Eldo detects the -adit flag, it executes the partitioning directives and sends any ADiT designated blocks to ADiT. What is left will be simulated in Eldo.

- -aditbb

As above, but sends blocks to ADiT in black-box mode without first parsing them.

- -ai veriloga_dir_name

Defines a repository directory for compiled Verilog-A models (.ai) and compilation files (. $\log$ and .info). If the specified directory does not exist, then it is created. By default, without this flag, Eldo calls the Verilog-A compiler without any argument, thus .ai files are
created in the working directory. This argument has precedence over netlist instructions. This argument applies to both .verilog and .use_verilog commands and is only taken into account when -vlac is specified.
The name of the output files will be extracted from the .VERILOG command. For example:

```
.VERILOG -o dummy/module.ai resistor.va
eldo -vlac -ai test ...
```

Eldo will create output file test/module.ai.

- -alter alter_name | alter_index

Allows running one specific .ALTER section by specifying it's name or index, without first running the main netlist. The .chi file and std output indicate that Eldo is only running a specific .ALTER due to this command line flag. Specifying an alter_index of 0 means the normal run without any alters; everything in the netlist is simulated except the modified rerun alter statements.

- -ascii

Forces Eldo to store the results including the printing of the output curves in the ASCII output .chi file, see also "ASCI I" on page 998. The size of this file can increase significantly for large simulations when these results are printed inside it.

- -b

Runs the simulation in the background, batch mode. Eldo will return the command prompt during simulation. The simulation cannot be terminated using $\mathrm{Ctrl}+\mathrm{C}$. A log of the simulation will be written to a $\log$ file which can be specified with the -l log_filename flag. You can set the $A M S \_U S E R$ environment variable to an email address to receive an email notification once the simulation has finished.

- -checksyntax

Forces Eldo to only parse the netlist and elaborate the design without performing simulation. Eldo will perform a syntax check of the netlist and generate warnings and errors as necessary.

- -clean

Remove all old intermediate files for the simulation filename specified. Useful for cleaning up old intermediate simulation files left around after a crashed simulation.

- -cntthread

Checks how many CPUs Eldo can access on a multi-processor machine when using -mthread. Returns details about the computer architecture. Eldo will share computer resources for multi-threading a single DC or TRAN simulation.

See "Multi-Threading Eldo Simulations" on page 58 for a full description of multithreading in Eldo.

- -compat

For simulator compatibility the -compat runtime flag can be specified, or alternatively the option compat command. Provides HSPICE compatibility. When Eldo is invoked with this argument, the main effect is that it accepts some HSPICE syntax. Full details are provided where applicable throughout this manual. For more information and a full list of the effects this flag/command option has, see "HSPICE Compatibility" on page 1373.

Flag -compat is equivalent to setting both -compmod and -compnet flags shown below:

- -compmod

Triggers only the automatic conversion of models (can alternatively be set with option COMPMOD). Provides HSPICE models compatibility.

- -compnet

Causes the netlist to be interpreted as compatible format, but the models themselves are treated as Eldo SPICE models (can alternatively be set with option compnet). Provides HSPICE netlist compatibility.

For more information and a full list of the effects the compxxx flags/command options have, see "HSPICE Compatibility" on page 1373.

- -convert_iic src_file dest_file

Converts a compressed file into a full ASCII file (names expanded and double values stored in ASCII). cir_filename should not be specified with this argument. src_file is the name of the file with information saved using either the . SAVE or . TSAVE command, a iic file is the default extension when saving a simulation run. dest_file is the destination ASCII filename. If dest_file already exists, the user is warned and prompted whether or not to overwrite it.

-     - cou

Generate output in binary Cou format file, see also "COU" on page 1011. This can also be specified using the invoke command -gwl cou. When JWDB output is not disabled, the .cou database will only contain real and imaginary parts of complex waveforms. To avoid this limitation, use -jwdb_nocomplex or -nojwdb.

- -cou47

Forces Eldo to create a different .cou file format (4.7). This format allows faster loading of a large database with many curves and/or several simulations from which only a few number of curves should be loaded. Only for use when cou output format is specified.

Refer to the Eldo cou Library User's Manual for further information.

- -couext

Merge extractions. Forces Eldo to dump .extract/.meas information into the .wdb or .cou file rather than in the .ext/.meas file. See also -nocouext.

- -createoutpath output_dir_name

Directory in which all output files are created. If the output directory specified does not exist, it is created. If not specified, output files are created in the same directory as the .cir input file. See also -outpath.

- -dbledefs

Allows several definitions of the same . subckt or of the same model to be accepted. This works only when Eldo is called using the -parse_only flag.

- -dbp

Forces AC output to be (DB, Phase) by default. See also -ri.

## Note

The command $\operatorname{VDB}(x)$ will always dump $\operatorname{VDB}(x)$. Flag -dbp (and -ri) apply to . probe ac $\mathrm{V}(\mathrm{X})$ for instance.

- -dump_file_list file

Generates a file containing all the files opened by Eldo (except temporary Eldo files) for a simulation. Useful for packaging an Eldo testcase. If a filename is not specified, then the netlist name is used with the extension .files_dump. If a relative path is specified then the file will be generated from the directory specified in -outpath output_dir_name.

The generated file contains all the absolute names of the opened files and is sorted by path and then by name (case ignored). Only one file is generated even if there are .alter statements or multiple netlists in the source file.

This can also be specified through an option, see also "DUMP_FILE_LIST" on page 1011.

- -d | -define macro

Define a macro at invoke time. Allows the user to define variables used by the preprocessor. See "Directives Interpreted by the Eldo Parser (Default)" on page 75 and "Directives Interpreted using the C Pre-Processor (-E/-EE Arguments)" on page 77.

-     - E

Allows extended use of pre-processor commands to define macros and replace them inside the netlist. Only the main netlist is sent to the C pre-processor. See "Directives Interpreted using the C Pre-Processor (-E/-EE Arguments)" on page 77.

- -EE

Allows extended use of pre-processor commands to define macros and replace them inside the netlist. The main netlist and all include files are sent to the C pre-processor. See "Directives Interpreted using the C Pre-Processor (-E/-EE Arguments)" on page 77.

- -eil file

Used to invoke Eldo in the interactive mode. Commands will be read from the specified file at invocation.

- -extract filename

Activates extraction mode (perform measurements using waves stored in .cou or . $w d b$ files). Eldo only performs the .EXTRACT commands, without performing the simulation(s). Eldo will decorrelate the simulation from the extraction. filename is the name of an EZwave .$w d b$ output file created from a previous simulation using the .PLOT/.PROBE command. Required. The extractions in the netlist will be solved using the corresponding waves contained in this file. Multiple levels of extraction are not supported with the -extract flag. This functionality can also be specified with the netlist command . Еxtmod, see ".EXTMOD" on page 636.

- -ezwave

Displays Eldo simulation results in the EZwave waveform viewer while the simulation is running (marching waveforms). This option automatically enables option -gwl jwdb if required. Eldo will plot the waveforms as defined in the netlist. When the simulation is complete, Eldo exits but EZwave remains displayed.

- -float

Forces Eldo to create $. w d b / . c o u l . f s d b$ files containing FLOAT rather than DOUBLE values, which results in saving $50 \%$ of the disk space. This is useful when it is known that the output file will be very large. However, for FFT, floating numbers are sometimes inappropriate as they cause a loss in accuracy. Note this flag was previously named -couf.

- -gwl gwl_lib_name

Forces Eldo to generate output in the required format (JWDB, and so on).
-gwl jwdb
Generate JWDB format files (extension . $w d b$ ). This is always generated by default, see also "JWDB" on page 1012.
-gwl cou
Generate binary Cou format file, see "COU" on page 1011. When JWDB output is not disabled, the .cou database will only contain real and imaginary parts of complex waveforms. To avoid this limitation, use -jwdb_nocomplex or -nojwdb.
-gwl csdf
Generate CSDF format file. CSDF is the Common Simulation Data Format, see
"CSDF" on page 1011.
-gwl fsdb
Generate FSDB format for nWave, see "FSDB" on page 1011.
-gwl psf
Generate binary Cadence format (used with Artist Link), see "P SF" on page 1014.

```
-gwl psfascii
```

Generate Cadence format in ASCII, see "PSFASCII" on page 1015.

```
-gwl psfop
```

Generate output for OP data in binary Cadence format (used with Artist Link). Can be used if PSF files are required for back-annotation of the OP results.
-gwl psfasciiop
Generate output for OP data in ASCII Cadence format (used with Artist Link). Can be used if PSF files are required for back-annotation of the OP results.
-gwl wdf
Generate WDF format for SPICE Explorer viewer, see "FSDB" on page 1011. This format is available only for Linux 32-bits and Sun 32-bits.

- -h hostname

Run the Eldo simulation using rsh (remote shell) on the machine (CPU) specified by hostname. Eldo recognizes the environment variable MGC_DESIGN_KIT (defined by IC Flow tools) if set, and uses it in remote simulations.

- -hdlpath veriloga_path

Specifies the search path for Verilog-A files. Used in conjunction with the .hDL and .VERILOG commands. See ".HDL" on page 678 and ".VERILOG" on page 933 for further information. The directory search order for Verilog-A files is:

- current directory
- path defined by the argument of -hdlpath


## Example:

```
    eldo test.cir -hdlpath ./lib/veriloga_src
```

- -help [commands|devices|sources|manual]

Online help. See Command Line Help.

- -i cir_filename

Input .cir file name. The .cir input file is mandatory and so this flag identifier is optional. By default, the first parameter in the command line is taken to be the cir_filename.

- -inter

Used to invoke Eldo in the interactive mode. Commands are sent interactively instead of sending the commands in the netlist.

- -isaving [val]

Specifies the "spill" threshold. Loads Eldo in incremental saving mode. Incremental saving allows the user to save the waveform data to a . $w d b$ file when the Joint Wave DataBase (JWDB) reaches the threshold specified (in bytes). The default value is 100 MB . Identical to -jwdb_threshold except for the default unit.

- -jwdb_config swd_filename

The.$s w d$ (saved window database) file specified in this argument may be the result from a previous EZwave session. The page composition of the netlist will be replaced by the one specified in the.$s w d$ file. Waveforms resulting from expressions or measurements will be "replayed" using new waves.

- -jwdb_extensions

Enables modifications in the way results are stored inside.$w d b$ files. The compound waveform is not created when .MC irun $=\mathrm{x}$ is used (since this is a single simulation), this can alternatively be set with option JwDb_extensions $=1$, see
"JWDB_EXTENSIONS=0|1" on page 1001).

-     - jwdb_nocomplex

Disable the generation of complex waves (can alternatively be set with option
NOWAVECOMPLEX).

- -jwdb_norffolder

Disable storing RF results in separate folders within the JWDB database. Instead results will be added to the AC and TRAN folders.

- -jwdb_servermode

Specifies the JWDB server launched by Eldo can be re-used by other simulations. Useful data is stored in a file pointed to by the environment variable $A M S \_W D B S E R V E R \_I N F O$, its default is $\$ H O M E /$.ezwave/jwdbserver.info. In this mode, the JWDB server will exit after the time specified by this environment variable if Eldo is not using it. Default is 60 minutes. See also Eldo Simulation in the EZwave User's and Reference Manual.

- -jwdb_threshold [val]

Loads Eldo in incremental saving mode. Incremental saving allows the user to save the waveform data to a.$w d b$ file when the Joint Wave DataBase (JWDB) reaches the threshold specified (in Megabytes). The default value is 100 MB . Identical to -isaving except for the default unit.

- -l log_filename

Specifies the log file name for a background, batch mode simulation (-b). If not specified, the log file is set to eldo_<PID>.log, where PID is the process identifier. Most commonly used in batch mode, but can also be specified in normal simulation mode.

- -lib object_library_dir_name

Name of the directory containing Eldo object library files for dynamic linking. This option is typically only used for Eldo-UDM/GUDM/UDRM analog behavioral modeling. Eldo will search for the specified directory and then search for Eldo library files (libeldo*) inside this directory, if either of these are not found Eldo will issue a warning. If not specified, the directory is set to: $\$ M G C \_A M S \_H O M E / \$ A M S \_V C O / l i b$ where $\$ A M S \_V C O$ is a runtime environment variable referring to the platform type, for example, ixl for Linux 32-bit.

- -libinc

Specifies that the full contents of every library are read by Eldo in one pass upon completion of reading the input file. This was the default mechanism in the v5.8 version of Eldo. All the libraries (. LIB ) are included without filtering the objects (model, card, or subcircuit) that are not used in the specific netlist. See "LIBINC" on page 966.

- -m subckt_name

Macro simulation. Specifies that all the devices at the top of the circuit (except voltage and current sources) are ignored, and the subcircuit specified subckt_name becomes the toplevel of the circuit. This can be useful for subcircuit testing.

- -m53

Specifies the ruling surrounding the M factor should be as it was for versions of Eldo before and including v5.3, see "M53" on page 979.

- -mgls_async

Allows asynchronous communication between the MGLS license manager and Eldo. Only use this argument if Eldo hangs at the end of a simulation on a multi-processor machine.

## Note

For safety, this argument enables the license manager to queue the license requests when needed. Therefore, if Eldo attempts to checkout licenses faster than they are checked in, Eldo will wait until new licenses are available.

- -mthread

Activates multi-threading for a single DC or TRAN simulation. Eldo will share computer resources on a multi-processor machine. Eldo will make use of all the possible CPUs on the machine. See also option "MTHREAD" on page 954.

See "Multi-Threading Eldo Simulations" on page 58 for a full description of multithreading in Eldo.

- -no_nominal_alter

Bypass the "nominal" run in a netlist containing .ALTER commands, can also be specified with .option NO_NOMINAL_ALTER.

- -no_sst_mthread

Deactivates multi-threading for a Steady-State simulation. See also Multi-Threaded Simulation Options (sst_mthread) of the Eldo RF User's Manual.

- -noascii

Prevents plot/print output waveform information from being produced in the ASCII output (.chi file), see also "NOASCII" on page 1004. The file is still created, but the size can be significantly reduced for large simulations when these results are not printed inside it. Eldo default behavior is with option NOASCII set so this flag should not be required.

- -nocatmx

Disables merging devices in parallel. See also option "NOCATMX" on page 989. For further details see "Merging Devices in Parallel" on page 120.

- -nochi

Prevents ASCII output from being produced (no .chi file is produced).

- -noconf

No confirmation. When stopping a simulation run with Ctrl-C, then Eldo exits with no confirmation. Also, it will not ask whether or not to re-enter FAS debugger, if necessary. This option is used in the Artist Link integration. Eldo automatically creates a save file when interrupted whenever a signal interrupt is received by Eldo, even if Eldo does not run in interactive mode (such as when running with LSF or Sun Grid).

- -nocouext

Forces Eldo to dump .extract/.meas information into separate files .wdb (or .cou) and .ext/.meas files rather than merged. See also -couext.

- -noerrmlog

Disables the creation of the error message manager log file (named <cirfile>.errm.log).
This file contains the warning/error messages which are used by the error message manager.

- -nogwl

All output files are generated except waveform files (.cou, .wdb, .tr0...)

- -noinit

Disable loading the eldo.ini file.

- -nojwdb

Disable the creation of.$w d b$ files (can alternatively be set with option noswde).

- -nostver

Disables the STMicroelectronics version of Eldo. Further information can be found in "STMicroelectronics Models" on page 1509.

- -o output_filename

Output .chi file name. If not specified, the .chi file is set to cir_filename.chi. output_filename has to be the full pathname of the ASCII output file. If output_filename does not contain any ' $/$ ' character (if output_filename is just a filename with no path), then any specified output_dir_name string will be used to create <output_dir_name>/<output_filename>.

- -opseldo_jwdb_run

Organizes the Waveform List of EZwave in a different way allowing easy access to results for different optimizer runs (can alternatively be set with option opseldo_JwDb_RUN, see "OPSELDO_JWDB_RUN" on page 1009).

- -out out_filename

Specifies the file name for all simulation output files. If not specified, files will use the default of cir_filename. A path can be defined as long as the directory exists. By default, the files are created in the same directory as the .cir file.

- -outname out_filename

Specifies the file name for simulation output files (.swd, .wdb, .cou). If not specified, files will use the default of cir_filename. A path can be defined as long as the directory exists. By default, the files are created in the same directory as the .cir file.

- -outpath output_dir_name

Directory in which all output files are created. If this flag is not specified, output files are created in the same directory as the .cir input file. If the output directory specified does not exist, it is not created, use -createoutpath instead. The final character of output_dir_name must be a forward slash ' $/$ '. If omitted, this will be added automatically.

- -ovstatus

Causes Eldo to dump at the end of the standard output (stdout) transcript some lines summarizing the status of the simulation. For example:

```
Simulation finished.
There are 3 parsing warning(s).
There are 1 simulation error(s).
```

The first line indicates the simulation has finished and the output file transcript is complete, with or without errors and warnings. The second line indicates the number of parsing errors or warnings. The third line indicates the number of simulation errors or warnings.
This can be useful if using a browser to analyze the status of a run. If there are nonconvergence errors, then in addition to the above lines, an extra line will be displayed:

```
including %ld simulation non-convergence error(s).
```

where $\%$ ld is the number of errors.

- -parse_only

Forces Eldo to only parse the netlist, generate warning and errors if any, and exit before the generation step (elaboration of the design).

- -plspath dir_name

Directory in which .pls files, generated by S-parameter file conversion, are created. By default, .pls files are created in the same directory as the.$s 4 p$ or .par files. See "Working with S, Y, Z Parameters" on page 1041.

- -probeop2

Eldo will generate a circuit.opx file, where x is the index of the run, in which DCOP information will be dumped. This file is an ASCII file which is read by the DA-IC environment. The content of this file is similar to that created when option probeor is used, but there is some additional information which is dumped: temperature, node
information, and now current out of X leaf-instances (leaf-cells are instances which do not call any other X instances).

- -queue

If there is no license available for Eldo, the job will be queued. Used for batch runs.

- -restart ["[save_file] [file=wfile]"]

Restarts a simulation run with information previously saved using the . SAVE command. The quotes are mandatory if more than one argument is specified. See ".RESTART" on page 854 for further information.

- -ri

Forces AC output to be (real, ImAg) by default. See also -dbp.

## Note

The command VDB(x) will always dump VDB (x). Flag -ri (and -dbp) apply to . PROBE AC $\mathrm{V}(\mathrm{X})$ for instance.

- -savetime time

Creates a .sav file which saves the context of a simulation every time hour of CPU time used in a transient analysis. If the system crashes during a run, the simulation may be restarted from the last saving time. See ".SAVE" on page 857 for further information.

- -searchpath path_list

Libraries and include files are searched inside the specified path when not found. There is no limit on the number of search paths that can be used. This has the same effect as SEARCH=path1 option, see "SEARCH=path1 [\{:path2\}]" on page 1022.

- -silent

Disables all displays to the standard output.

- -sp spectre_file

Use a Spectre netlist as input. Eldo will call the spect2el script to convert netlists from Spectre format (Spectre language syntax) into Eldo format (Eldo syntax). spect2el generates several files that are used to map the Spectre name to a SPICE name. This will also avoid the reconversion of the Spectre files if nothing has changed in them. spectre_file must be specified with an extension. No guess is made on the possible extension. If the filename is specified without its extension it will lead to an error.
See "Spectre Compatibility" on page 1395 for further information.
-i spice_command_file
Used with the -sp argument when a Spectre netlist is the input. spice_command_file must be specified with an extension. No guess is made on the possible extension. If the filename is specified without its extension an error will be generated. The spice_command_file must not include the spectre_file. Eldo will automatically
perform the link between these files. Including the Spectre file will not work and the simulation will stop.

```
-s2emode 2|1
```

Used to switch between the old (pre-2009.1) and new converter. Optional. Used with the -sp argument when a Spectre netlist is the input. Set to 1 to run the old converter. Set to 2 (default) to run the newer one, which provides speed and robustness advantages. If errors occur when -s2emode 2 is specified, a file named spect2el.error will be generated clearly describing the errors.

```
-clean_sp
```

Used with the -sp argument when a Spectre netlist is the input. Removes all the files generated by spect 2 el . As a consequence, if you want to relaunch the simulation on that design, the converter will reproduce the work. This will increase the overall simulation time.

```
-spectre_out pathname
```

Define the path in which the files generated by spect2el reside. Optional. Used with the -sp argument when a Spectre netlist is the input. Eldo creates pathname automatically if it does not exist. If -clean_sp is also specified, Eldo clears the files/sub-directories under pathname, while pathname itself is not removed after simulation. By default, pathname is identical to the one specified by -outpath.
-sp_plot 2|1|0
Controls the conversion of Spectre save statements into Eldo .PRINT, .PLOT and . PRobe commands as below:
if -plot 0 , the converter will convert the save statement into .PRINT (default). if -plot 1, the converter will convert the save statement into . РLOт. if -plot 2, the converter will convert the save statement into .PROBE.

- -spiout

Causes the netlist to be printed without any line numbers in the output file.

- -spmodel <subckt_name1> -spmodel <subckt_name2> ...

Used in conjunction with the .hds command. The subcircuit name specified on this flag has higher priority than Verilog-A modules of the same name when both exist. Only one subcircuit name can be specified on each -spmodel flag. Multiple names require multiple flags. See also "SPMODEL=subckt_name" on page 1020. See ".HDL" on page 678 for further information. For example:

```
.hdl opamp.va
.subckt myopamp a b c
....
.ends
x1 1 0 2 myopamp
eldo test.cir -spmodel myopamp
```

If the Verilog-A file opamp.va contains a module named myopamp Eldo will use the subckt definition instead of the Verilog-A module of the same name. In this configuration the following command is equivalent:

```
eldo test.cir
```

Eldo will first look first for a subckt definition for the X instances. If one is not found or if a vamodel is provided then Eldo will look for Verilog-A modules.

- -ssh hostname

Run the Eldo simulation using ssh (secured shell) on the machine (CPU) specified by hostname. Eldo recognizes the environment variable MGC_DESIGN_KIT (defined by IC Flow tools) if set, and uses it in remote simulations.

- -ssim

Runs the Motorola (SSIM model) version of Eldo. See also "MOTOROLA" on page 950. This model is only supported on Solaris platforms in Eldo 32-bit mode. Further information can be found in "Motorola SSIM Model (Eldo Level 54 or SSIM)" on page 276.

- -stat [-statfile filename]

Writes design, elaboration, and simulation information to a statistics file. The statistics file is a summary of the simulation activity and is usually quite small. The file should be sent to a support engineer to aid debugging of a design in the event of a problem. The information will not be written to the file if an error occurs during elaboration. For a description of the statistics file, see "Statistics File" on page 63.

- -stver

Runs the STMicroelectronics version of Eldo. Further information can be found in "STMicroelectronics Models" on page 1509.

- -tuning [FAST|STANDARD|ACCURATE|VHIGH] -tuning [BACKANNOTATE]

Selects the default mode of operation of Eldo as regards to precision and speed, see "TUNING=[FAST|STANDARD|ACCURATE|VHIGH] [TUNING=BACKANNOTATE]" on page 972 . The -tuning flag overrides any tuning option settings inside the netlist.
The -tuning flag only accepts one argument at a time, so the option has to be repeated when combining arguments, for example:
-tuning ACCURATE -tuning BACKANNOTATE

- -use_proc n | HALF \| MAX k | ALL | HYPER

Activates multi-threading for a single DC or TRAN simulation. Eldo will share computer resources on a multi-processor machine depending on the user-specification below.
n
use n processors
HALF
use half the processors

MAX k
use a maximum of k processors
ALL
use all processors except hyperthreading
HYPER
use all processors including hyperthreading processors
See "Multi-Threading Eldo Simulations" on page 58 for a full description of multithreading in Eldo.

- -useht

Activates hyper-threading to be taken into account when counting the number of processors. By default, Eldo does not take hyper-threading into account, because it is not always efficient to do so. Must be used in conjunction with multi-threading, see -mthread.

See "Multi-Threading Eldo Simulations" on page 58 for a full description of multithreading in Eldo.

- -usethread val

Activates multi-threading for a single DC or TRAN simulation. Eldo will share computer resources on a multi-processor machine. Eldo will make use of the number of CPUs specified with this flag. This is useful if you want to use a smaller number of threads than the number of available CPUs. For example on a 16 CPU machine, you might only want to use six. The number specified can exceed the number of CPUs available, but this is not recommended. See also "USETHREAD=VAL" on page 962. -usethread takes priority over -mthread when both flags/options are specified.
See "Multi-Threading Eldo Simulations" on page 58 for a full description of multithreading in Eldo.

- -v

Returns the software version number. No simulation is performed.

- -vamodel <mod_name1> -vamodel <mod_name2> ...

Used in conjunction with the .hDL command. The Verilog-A module name specified on this flag has higher priority than a subcircuit of the same name when both exist. Only one module name can be specified on each -vamodel flag. Multiple names require multiple flags. See also "VAMODEL=mod_name" on page 1020. See ".HDL" on page 678 for further information. For example:

```
.hdl opamp.va
.subckt myopamp a b c
....
. ends
x1 1 0 2 myopamp
eldo test.cir -vamodel myopamp
```

If the Verilog-A file opamp.va contains a module named myopamp Eldo will use the Verilog-A module myopamp instead of the subckt definition of the same name.

- -verbose

Forces Eldo to display more detailed reporting with some information messages in the standard output terminal. See also "VERBOSE" on page 997. Eldo will print hints about syntax which is valid but ignored if the appropriate analysis is not found in the netlist. For example:

```
Warning 10001: No optimization command has been found in the netlist.
As a consequence:
    1) .option OPSELDO_NETLIST is ignored
    2) .PARAMOPT are interpreted like .PARAM using the initial value,
        or ignored if no initial value has been specified.
    3) GOAL=MINIMIZE is ignored on measurement FOO
    4) GOAL is ignored on measurement FOO2
    5) UBOUND is ignored on measurement FOO3
    6) GOAL=MAXIMIZE is ignored on measurement FOO4
Warning 10002: COMMAND .MC has not been found in the netlist.
    As a consequence:
        1) .option DISPLAY_CARLO is ignored
```

- -vlac

Run the pre-2009.1 Verilog-A compiler. Refer to the Eldo Verilog-A User's Manual for further information.

- -wB cou_filename

Output .cou file name. cou_filename has to be the full pathname of the binary cou output file. If cou_filename does not contain any ' $/$ ' character (if cou_filename is just a filename with no path), then any specified output_dir_name string will be used to create <output_dir_name>/<cou_filename>. This flag should not be used with JWDB output.

- -wdl_timeout time

Instructs Eldo to wait the specified time seconds for a response from the JWDB server. By default, the timeout is 120 seconds.

## Viewing Eldo Documentation

This release includes the Mentor Graphics Documentation System. The System consists of the InfoHub ${ }^{\mathrm{TM}}$ (index), as well as PDF and HTML documents. You access the documentation system using any of the following methods:

- mgcdocs shell command from a UNIX or Linux shell window
- Start > Mentor Graphics > AMS_<release>>documentation menu from Windows


## Command Line Help

A simple online help can also be accessed from the command line with:

```
eldo -help [commands|devices|sources|manual]
commands Opens Simulator commands quick help (PDF)
devices Opens Device models quick help (PDF)
sources Opens Sources and Macromodels quick help (PDF)
manual Opens full Eldo User's Manual (PDF)
```

Each of the first three help options will open a link document in Acrobat Reader, which will then allow you to select the command, device model, source or macromodel you require information on.

Entering eldo -help without any option will display the list of available topics.
This flag can be specified without the cir_filename which is usually mandatory.

## Multi-Threading Eldo Simulations

You can activate multi-threading for DC and transient Eldo simulations to speed-up simulation. Eldo will share computer resources on a multi-processor machine. Eldo will make use of all the possible CPUs on the machine.

Eldo will then use these processors as much as possible. It will share the work between the different CPUs in order to speed-up simulation. Note that the CPUs should not already be in use, otherwise simulation will be slower.

Multi-threading is activated with the -use_proc n \| HALF | MAX k | ALL \| HYPER command line argument, which provides you with the flexibility to choose how many of the processors to use. You can specify the number of processors, half the processors, a maximum of k processors, all processors except hyperthreading, or all processors including hyperthreading processors.

Multi-threading can also be activated with the -mthread command line argument, or with option MTHREAD.

Another alternative activation is with the -usethread val command line argument, or option USETHREAD=VAL. Eldo will make use of the number of CPUs specified with this flag/option. This is useful if you want to use a smaller number of threads than the number of available CPUs. For example on a 16 CPU machine, you might want to only use six. The number specified can exceed the number of CPUs available, but this is not recommended. If you attempt to set more than twice the number of processors Eldo detects, then it will be capped to twice the number of processors.

## Note

-usethread takes priority over -mthread when both flags/options are specified.

Statistics, generated at the end of simulation, show how many CPUs have been used for the current simulation. This number will also be displayed at the beginning of the TRAN simulation.

The -cntthread argument can be specified to provide more details about the computer architecture, for example:

- Bi-Xeon dual core with no hyper-threading

```
Number of physical processors : 2
+ Hyper-Threading Technology : disabled
+ Number of cpu cores : 4
+ Number of logical processors : 4
```

- Bi-Opteron

```
Number of physical processors : 2
+ Hyper-Threading Technology : N/A
+ Number of cpu cores : N/A
+ Number of logical processors : N/A
```

- Bi-Xeon (PIV) with hyper-threading

```
Number of physical processors : 2
+ Hyper-Threading Technology : enabled
+ Number of cpu cores : 0
+ Number of logical processors : 4
```

Eldo will make use of the multi-thread capability of the machine it is running on only if all the following conditions are met:

- the -uSe_proc flag has been set, or the mthread flag has been set (via option or at invocation)
- the machine is a multi-CPU machine
- the circuit contains devices which are thread-safe
- the circuit contains more than 1000 MOSFET devices per thread (this is not a strict rule, simply a guideline to the design complexity required for multi-threading; it can be used on a circuit that contains less MOSFETs but with many parasitic resistors/capacitors)

If the circuit does not contain any thread-safe device, multi-threading will be ignored. Threadsafe devices are BJT, diode, resistor, capacitor, and MOSFET exclusively. A few models of these categories are not thread-safe, and are therefore handled in a single processor. Eldo will notify when it cannot apply thread optimization on models. Thread-safe and non-thread-safe models can be used in the same circuit.

Eldo automatically adjusts the number of threads so each processor has enough work to do. If Eldo cannot set the number of threads so that each thread has approximately 1000 MOSFETs (or parasitic resistors/capacitors), then multi-threading will be disabled.

When multi-threading is activated, the CPU time reported by Eldo is the sum of the CPU time of all threads. This time will be much higher than the GLOBAL ELAPSED time reported by Eldo. The below examples is an extract of a transcript showing this:

```
# ----- Summary run statistics ----
# Global Threads cpu Time 72h 27mn 31s 620ms
# Global Elapsed Time 47h 36mn 21s
```

Hyper-threading can also be taken into account in conjunction with multi-threading by specifying the -useht command line argument. By default, Eldo does not take hyper-threading into account, because it is not always efficient to do so.

## Notes

- Multi-threading and DC computation

DC computation can be very sensitive to numerical noise (because of the algorithm used), and as multi-threading cannot preserve the order of operations, it is possible to obtain different DC computation times and even different DC solutions found from one run to another. This can occur if the circuit has multiple valid DC points, and is the same whether using multi-threading or not.

## Linux

When an application is multi-threaded on Linux, the "top" or "ps" operating system commands may return misleading information, depending on the version of the library libpthread.so provided with the Linux kernel. Each thread may appear as a separate process, each of them consuming the same memory resources. You should consider that the application only uses the resources indicated for one "process." Do not consider the addition of all indicated processes, which in reality correspond to the threads.

## Eldo Initialization File

An Eldo system initialization file named eldo.ini can be created. This file will be interpreted and loaded at the very beginning of each simulation. "Loading eldo.ini" is displayed whenever a valid eldo.ini file is found. Specifying the -noinit argument will disable the loading of the eldo.ini file.

This initialization file can be used to specify some configuration options always included in the .cir file.

The search order is:

- path specified by environment variable \$ELDO_INI_FILE_PATH
- current directory
- \$HOME directory

This file is separated into blocks which are specified using a tag (no mandatory order):

- environment variables definition (after tag [env])
- arguments for command line (after tag [argu]); arguments in this section are interpreted before any Eldo command line arguments, Eldo command line arguments have higher priority
- netlist commands (after tag [eldo]); commands in this section are interpreted as if they had been included in the netlist with a . INCLuDE command

A typical eldo.ini file may look like:

```
# This line is a comment
[env]
# There must be no blanks between variable name, equal sign
# and variable value
OPTION_DIR=.
MODEL_DIR=../models
LIB_DIR=../libs
[argu]
-outpath $OPTION_DIR/results
-gwl jwdb
-compat
[eldo]
.option noascii notrc
.include $OPTION_DIR/options.inc
.option post probe
```


## Location Maps

Location maps are used to replace prefixes of physical pathnames with environment variables (soft pathnames). The location map defines a mapping between physical pathname prefixes and environment variables. IC Flow users can benefit from this functionality to run Eldo directly on a DA-IC generated netlist.

By default, Eldo will search for a location map file in the following locations, in order:

- the filename specified by option uSe_LOCATION_MAP in the .cir file, if not found Eldo displays a warning message
- the path stored in the environment variable \$MGC_LOCATION_MAP
- the netlist directory (./mgc_location_map)
- your home directory ( $\left.\sim / m g c \_l o c a t i o n \_m a p\right)$

When option USE_LOCATION_MAP is specified, a warning message is displayed if Eldo does not find a location map file. When option USE_LOCATION_MAP is not specified, no warning message is displayed by Eldo.

You can disable the load of the location map file by specifying the -ignore_location_map command-line argument or specifying option IGNORE_LOCATION_MAP in the netlist.

## Location Map Structure

The purpose of the location map file, in the Eldo context, is to be able to map a soft path with a hard path.

The location map file structure is as follow:

- The first line is a header. That header is not mandatory with eldo which always ignore the first line but is necessary if that file has to be used inside DA-IC. In such a case, please refer to the DA-IC Design Manager User's Manual to use the right header.
- The file is then composed of a set of soft pathname / hard pathname and comments.
- A soft pathname always begins with a dollar sign (\$).
- A hard pathname always begins with the customary slash (/)
- A comment always begins with sharp (\#)

The user can specify zero, one, or several hard pathname for a soft pathname.
Here is an example of mgc_location_map file:

```
MGC_LOCATION_MAP_2
#Here is a soft pathname with no hard pathname.
#In such a case, there must be an environment variable named REF_DIR
#and eldo will import the hard pathname contained in that variable
#and will map REF_DIR with that imported hard pathname
$REF_DIR
#Here we have another soft pathname mapped with two hard pathnames
$SOURCE_PROJECT
/home/user/projxxx
/mnt/remote_device/home/user/projxxx
```

Note: when several hard pathnames are given for a soft pathname, only the first one will be used by Eldo. Therefore that pathname must be visible from all computers that are going to use that location map file. Giving several hard pathnames for one soft pathname is only valid in the context of DA-IC. Because, DA-IC can try, given a path, to find the mapped soft pathname. As mount points can be different according to the computer used
and the network structure, it might be necessary to specify all mount points of a given folder. But Eldo only tries to expand a soft pathname into a hard pathname to resolve a file name (in a .include statement for example). This is why the first path has to be visible whatever computer is used on the network. More details are available in the $D A$ IC Design Manager User's Manual.

- It is also possible to include files using the INCLUDE command:

INCLUDE <hard pathname to the location of the file to include>
The included files must not contain a header.

## Notes

- When a soft pathname is defined several times in the location map file, only the first definition is used, others are ignored.
- For a given soft pathname, if Eldo is unable to access to the specified hard pathname, a warning message is printed out (warning 939).
- If a given soft pathname already exists as an environment variable, Eldo always uses the value of the environment variable.


## eldo-stacktrace File

If an unexpected problem is detected by Eldo (for example, a message that reports an "Error Code"), the file eldo-stacktrace.dump or eldo-stacktrace.vstf will be generated in the output directory and the simulation will terminate. Include the eldo-stacktrace file along with the model causing the error when submitting your Service Request to Mentor support. For more information on Service Requests, please refer to the section Tracking Service Requests, DRs, and ERs of the AMS Release Notes.

## Statistics File

The statistics output file from Eldo can be useful to understand how a design behaves. It can help to monitor the simulation performance, determine circuit size impact on simulation, debug simulation slowdown, and determine which nodes and blocks should be treated for minimizing rejections. The content of the file is divided into the following main parts:

- General Design Info
- Tool Versions
- High-level Design Information
- Analog Elaboration Information

In the Elaboration and Simulation parts, statistics are grouped into three main categories:
Mixed-Signal, Digital, and Analog (SPICE, Fast-SPICE).

## Generation

The statistics file can be generated by launching Eldo with the -stat flag, see "-stat [-statfile filename]" on page 55.

By default, the output file is named:

```
<cir_filename>_<date>_<time>.stat
```

where cir_filename is the name of the .cir netlist file to be simulated. For example, eldo ad4b.cir -stat executed on June 242009 at 9.23am will generate a statistics file named ad4b_20090624_092325.stat. To specify a different filename, use the -statfile flag, for example, eldo ad4b.cir -stat -statfile ad4b.stat will generate a statistics file named ad4b.stat.

By default, the output file is generated in the directory where Eldo was launched. Specify the -outpath flag to generate the statistics file in a different location.

By default, a single statistics file is set to a maximum size of 50 MB . If the maximum size is reached, a new statistics file is created and a message appears in the transcript. The names of these files are of the format:

```
<cir_filename>_<date>_<time>.<n>
```

where $\langle\mathrm{n}>=1,2,3$, and so on.

## Content

Statistics files are divided into sections highlighted by asterisks.

## General Design Information

## Heading

```
***************************************
* General Design Info *
****************************************
```


## Content

- Design name: Netlist Design Name
- Machine: Machine and Platform information
- Starting time: Starting simulation time and date record


## Tool Versions

## Heading

```
***************************************
* Tool versions *
```


## Content

- Tool versions report


## High-Level Design Information

## Heading

```
***************************************
* High-level Design Information *
******************************************
```


## Content

- Eldo kernel options: a list of Eldo kernel options used for the simulation


## Analog Elaboration

## Heading

```
    ****************************************
* Elaboration: Analog
***************************************
```


## Content

- Listing of number of Nodes in Eldo/FastSPICE/Both/Total
- Number of nodes
- Number of device internal nodes
- Number of stimulus nodes
- Listing of number of Devices in Eldo/FastSPICE/Both/Total
- Number of resistors
- Number of capacitors
- Number of grounded capacitors
- Number of inductors
- Number of voltage sources
- Number of current sources
- Number of controlled sources (E/F/G/H)
- Number of diodes
- Number of BJTs
- Number of JFETs
- Number of MOS
- Number of switches
- Number of transmissions lines
- Total number of the above listed devices


## Memory Used During Elaboration

## Heading

```
***************************************
* Elaboration: Memory *
```


## Content

- Memory used in kB by the Eldo kernel
- Memory allocated and memory used in kB by EZwave and the JWDB server during the elaboration phase
- WDB file name
- Database name with the number of waveforms and the number of aliases


## SPICE Elaboration

## Heading

```
***************************************
* Elaboration: SPICE *
****************************************
```


## Content

This section is dedicated to the elaboration between Eldo and Fast-SPICE (ADiT) if any.

- A table, showing the ratio of the nodes and devices that are on the Eldo side and on the ADiT side.
- A list of the numbers of nodes:
- Number of Boundary OUT nodes: the number of nodes computed by Fast-SPICE (taking care of Eldo current loading of the Node) with values given to Eldo
- Number of Boundary IN nodes: the number of nodes computed by Eldo (taking care of the Fast-SPICE current loading of the Node) with values given to the FastSPICE solver
- Number of Boundary KEEP nodes: the KEEP nodes are OUT boundary nodes but declared as A2D nodes. There is no current on those nodes. The voltage values are directly fixed on the digital side.
- A2A - ELDO V Control nodes: the number of voltage sources which are used on the Fast-SPICE side but controlled by Eldo during the simulation
- A2A - High Coupling nodes: the number of highly coupled nodes between the FastSPICE and Eldo solvers (analog versus analog)
- Number of D2A supply nodes: the number of D2A boundary elements associated with V source nodes
- Number of D2A boundary nodes: the number of D2A boundary elements inserted between Eldo and Fast-SPICE
- Number of A2D boundary nodes: the number of A2D boundary elements inserted between Eldo and Fast-SPICE


## Chapter 3 <br> Eldo Control Language

## Introduction

The Eldo .cir control file contains all the information necessary to run an Eldo simulation. The Eldo Control Language is used to specify all circuit descriptions and simulation commands in the .cir file. The Eldo Control Language is a superset of the standard Berkeley SPICE 2G6 language. Standard Berkeley SPICE control files will thus be accepted by Eldo. However, Eldo provides additional features not available in SPICE. This chapter provides an overview of the .cir file structure and general aspects of the language syntax. The following chapters then provide full definitions of the Eldo control language syntax for device, source and macromodel instantiations, and all of the command set.

## Overview of the .cir File Structure

## Example

As in SPICE, the first line is treated as comment. See "General Aspects of the Language Syntax" on page 70 for descriptions of the syntax.

```
my_example_circuit
* Model definitions
.model m1 nmos level=3 vto=1v ! Example comment
*
+ uo=550 vmax=2.0e5 cgdo=0.4p
* Subcircuit definitions
.subckt inv 1 2 3
m2 2 1 0 0 m1 w=10u l=4u ad=100p pd=40u as=100p
m1 2 1 3 3 p1 w=15u l=4u ad=100p pd=40u as=100p
c1 2 0 0.5p
.ends inv
* Subcircuit calls
x1 1 2 6 inv
cload 4 0 1p
```

```
* Electrical source definitions
vdd 6 0 5v
vin 1 0 pulse (0 5 10e-9 5e-9 5e-9 30e-9 50e-9)
* Simulation options & commands
.tran 0.5n 100n uic
.ic v(1)=0
.plot tran v(1) v(2) v(3) v(4)
.print tran v(1) v(2) v(3) v(4)
.option eps=0.5e-3 tnom=50 list node
.end
```


## General Aspects of the Language Syntax

The following sections in this chapter provide a summary of the Eldo language syntax.
The later chapters in this manual contain the complete descriptions of all the devices, sources, macromodels and commands listed in the following pages. This chapter is designed as a quick reference to the syntax for these and is of use to the more experienced user.

See "Documentation Conventions" on page 38 for a detailed description of the meanings of the different fonts, brackets, and so on, used throughout this manual.

## First Line

The first line is format free and reserved for the circuit title. This line is mandatory and serves as the heading on graphical results output.

## Continuation Lines

The length of one input line is limited to 2000 characters. A line may be continued by using the + character at the beginning of the new line. In arithmetic expressions, this leading + sign will be ignored arithmetically and treated as a continuation. Two + signs may be placed together to both continue the line, and perform the addition operation.

## Comment Lines

A new comment line must begin with the * character. If the comment follows an Eldo statement on the same line (inline comment), it must begin with the ! (or, in some cases, the *) character. The inline comment character (! or *) must be preceded by a white space.
Otherwise, the ! or * character will be considered as a valid character that can, for example, be used in node names, or in other cases be ignored. The * character not allowed as an inline comment on .EXTRACT, .DEFMAC, .DEFWAVE, .MEAS, .OBJECTIVE, and .PARAM commands.

* <comment line>
<Eldo statement> ! <inline comment>


## Note

The inline comment character (! or *) must be preceded by a white space. If not, Eldo could ignore it in the case of a parameter value, or consider it a valid character in node names. For example, the first of the below lines is accepted, without any error or warning message, to be identical to the second ("5!" is interpreted as the number 5 and the 22 is parsed as the TC1 temp coefficient).
r1 1 2 5! 22

| $r 2$ | 2 | 5 | 22 |
| :--- | :--- | :--- | :--- | :--- |

A set of comment lines can also be grouped together into a block as shown below:

## \#com

A block of
comment
\#endcom
In these cases the * character is not needed.

## Component Names

Component names start with the component reserved characters and continue with an arbitrary sequence of alphanumeric characters, including $\%, \$, \#, \ldots$. Component names cannot be broken at the end of a line.

## Parameter Names

Parameter names may contain an arbitrary sequence of alphanumeric characters, including $\%, \$$, \#, _, !. Parameter names cannot be broken at the end of a line. Parameter names should not contain boolean operators. Such a name can be quite ambiguous.

## String Parameters

Eldo accepts quoted character strings as parameter values. These string values may be used for model names and filenames. To use a string as a parameter, enclose the string within double quotes, for example:

```
.param TT1="ResMod"
```

To maintain the case of the string enclose the string within double quotes first and then enclose within single quotes, for example:

```
.param TT2='"PwlModFile.src"'
```

A string parameter can be defined on multiple lines if the string on each line is enclosed within double quotes, for example:

```
.SIGBUS mybus base=bin TFALL=3n TRISE=3n THOLD=20n TDELAY=50n VHI=5 VLO=0
+ pattern $ (PAT)
.PARAM PAT= " 00000 00001 00010 00011 00100 00101 00110 00111 "
+ " 01000 01001 01010 01011 01100 01101 01110 01111 10000 10001 "
+ " 10010 10011 10100 10101 10110 10111 11000 11001 11010 11011 "
+ " 11100 11101 11110 11111 00000 00001 00010 00011 00100 00101 "
```

The space before the double quote at the right hand side is mandatory. Without it, Eldo will generate an error.

The value of a string is retrieved simply by specifying the dollar sign (\$) and parentheses ( ). Examples:

```
.param MOD="Pmos1"
m1 d g s b $(MOD) w=1u l=1u
.param STIMFILE='"Stim.txt"'
v1 1 0 pwl file=$(STIMFILE) R
```

String parameters can be used in .sIgbus or pattern sources. A sweep (for example . STEP) can also be made on string parameters.

## Reserved Keywords

Some keywords should not be specified in a . PARAM command. If they are then errors will be generated. See Table 10-21 and Table 10-22 on page 779.

## Node Name Conventions

Node names may contain an arbitrary sequence of alphanumeric characters and some nonalphanumeric characters including: !, \$, \#, , [ ], <>, :, <br>, /, |, +, -, *, \%.

The following characters are not allowed in node names: (), $\}, ',=$. Node names can not begin with any of the following characters: $*,+,-, \&, \mid, "$. Do not use the period character (.) in a node name because it is reserved as a hierarchy separator between a subcircuit name and a node name.

Node names cannot be broken at the end of a line. If the first character of a node name is numeric then it is forbidden for an alphabetic character to follow in the same name: all characters must then be numeric. Numeric characters can, however, follow an alphabetic character in the same node name.

| 1тото | Illegal node name |
| :--- | :--- |
| 123 | Legal node name |
| тото1 | Legal node name |

Whenever Eldo sees a node name with suffix " .0 ", Eldo assumes that node 0 was intended if the name also begins with an X , for example: C1 a XA. 01 p is identical to $\mathrm{C1}$ a 01 p . Alternatively, with syntax: C1 a a. 01 p ; a node named a. 0 is created as a regular node.

## Node Names Used Inside Subcircuits

If you wish to access nodes from a higher level of hierarchy than that in which they are defined, it may be done as shown in the following example:
X27.x113.n3 Legal node name

The node N3 is located within a subcircuit x 113 which, in turn, is located inside another subcircuit x 27 .

For more information about the usage of nodes inside subcircuits, please refer to ".SUBCKT" on page 898.

## Values

Values are always handled as real numbers. They may be specified in exponential notation or with scale factors.

## Model Names

Model names cannot start with a numeric. This causes compilation of the netlist to be broken, giving an error message.

## Scale Factors

For scaling, you can choose between the exponential notation, or one of the following:
Table 3-1. Scale Factors

| Symbol | Multiplier | Name |
| :--- | :--- | :--- |
| A | $1.0 \times 10^{-18}$ | atto |
| F | $1.0 \times 10^{-15}$ | femto |
| P | $1.0 \times 10^{-12}$ | pico |
| N | $1.0 \times 10^{-9}$ | nano |
| U | $1.0 \times 10^{-6}$ | micro |
| M | $1.0 \times 10^{-3}$ | milli |
| K | $1.0 \times 10^{3}$ | kilo |

Table 3-1. Scale Factors

| Symbol | Multiplier | Name |
| :--- | :--- | :--- |
| MEG | $1.0 \times 10^{6}$ | Mega |
| G | $1.0 \times 10^{9}$ | Giga |
| T | $1.0 \times 10^{12}$ | Tera |

## Notes

- Letters which are not scale factors are ignored if they immediately follow a number. Hence $10,10 \mathrm{~V}$ and 10 Hz all represent the same number, 10 . However, 10 A will be interpreted as $1.0 \mathrm{e}^{-17}$, because of the atto scaling factor.
- Letters immediately following a scale factor are ignored. Thus M, MA, MSEC, and MMHOS all represent the same scale factor, M.
- The scale factor m represents $1 \times 10^{-3}$ or "milli" units. $1 \times 10^{6}$ or "mega" units are specified using the MEG scale factor. This is commonly confused in SPICE syntax.
- Scale factors are not cumulative. кк is not meg, but к, since the second letter is ignored.
- M.K.S. units are used throughout the netlist.


## Directives

## IF/ELSE/ELSEIF/ENDIF Condition Statements

IF-ELSE-ELSEIF-ENDIF condition statements can be used inside the Eldo netlist, and can be used to instantiate devices depending on parameter size. ELIF and ELSIF keywords are also accepted as the ELSEIF condition.

- The IF-ELSE-ELSEIF-ENDIF section must not contain any command, otherwise unexpected results can be obtained. Warnings are issued in this case.
- The parameters used in expressions of if statements are evaluated during the parsing of the design only, even if these parameters are changed at run time (because of . STEP, for instance), then the design will not be changed, a message will be issued that the operation cannot be taken into account. The .ALTER mechanism should be preferred here.

Example of usage:

```
.subckt foo 1 param: p1 = 1
if (p1 >= 1.5)
r1 1 0 '2*p1'
else
r1 1 0 '3*p1'
```

```
endif
.ends
i1 1 0 3
x1 1 foo p1 = 3
.op
.end
```

In this example, rl value will be $6 \Omega$.

## Note

4 Errors are issued if ADMS is used, or if X or Y statements are present inside if-endif blocks.

## String Operator on If Expressions

It is possible to use C-like functions stremp and strnemp inside if statements used for netlist configuration. stremp and strncmp return " 0 " when the string matches, "not 0 " otherwise. Examples:

```
.param p1 = "myp1"
if (strcmp(p1,"myp1") == 0)
i1 1 0 1
else
i1 1 0 2
endif
r1 1 0 1
```

Here, il will be 1 A .

```
if (strcmp($(p1),"myp1") == 0)
i1 2 0 3
else
i1 2 0 4
endif
r1 2 0 1
```

Similarly, il will be 3A because the if statement is true.

## Directives Interpreted by the Eldo Parser (Default)

By default, (without the -E or -EE flag) Eldo understands the following simple pre-processor commands: \#if, \#define <name>, \#ifdef <name>, \#ifndef <name> \#else, \#endif.

These can be used to select a part of the netlist, for example:

```
#define NO_RESISTOR
#ifndef NO_RESISTOR
R1 A B 1k
```


## \#endif

. . .
A define can also be specified at invoke time with:

```
eldo <arguments> -define <name>
```

For example, -define foo on the command line is equivalent to \#define foo in the netlist. For both methods, the netlist statement \#ifdef foo will be true.

The \#if statement can be used for making complex conditional statements using logical operators: OR $\|$, AND \&\&; and comparison operators: not equal to $!=$, equal to $==$. The \#if directive can also be used in conjunction with the defined function, that is, if a \#define <name> is active, defined(<name>) returns 1 whatever value is assigned to <name>.

## Example

```
V1 1 0 1
#define U 0
#if (defined(U) || defined(A))
R1 1 0 1
#else
R1 1 0 2
#endif
.end
```

Because $U$ is defined in the above example, defined(U) will return 1 . The \#if statement is true and R1 will be set to 1 . When the \#if statement is substituted with: \#if (defined(U) \&\& defined(A)), the \#if statement will no longer be true because A is not defined. R1 would therefore be set to 2 .

## \#NETLIST_END and \#END_NETLIST_END Directives

Syntax:

```
#NETLIST_END
#END_NETLIST_END
```

Every line declared between these two directives is postponed until the end of the netlist (.END). This could be used, for example, to allow a .ALTER definition anywhere in the netlist.

If several \#NETLIST_END/\#END_NETLIST_END blocks are declared, they are treated according to their order in the design. These blocks can be defined in the top netlist or any included files. Nested \#NETLIST_END/\#END_NETLIST_END directives are ignored.

## Example

```
i1 1 0 dc 'p1'
.dc
```

```
#netlist_end
.alter
.param p1=3m
#end_netlist_end
.param p1=1m
r1 1 0 1
.extract dc v(1)
.alter
.param p1=2m
.end
```

In this example, three DC analyses will be performed: the first one using $\mathrm{p} 1=1 \mathrm{~m}$, the second one using $\mathrm{pl}=2 \mathrm{~m}$, and the last one using $\mathrm{p} 1=3 \mathrm{~m}$ which is defined in a \#netlist_end/\#end_netlist_end block.

## Directives Interpreted using the C Pre-Processor (-E/-EE Arguments)

For an extended use of pre-processor commands to define macros and replace them inside the netlist (see the example below), the -E or -EE flag needs to be specified. These are not the Eldo default because the parsing of large circuits may be significantly slower.

The -E flag forces Eldo to provide only the main netlist to the C pre-processor, whereas -EE ensures that all \#include filename statements will be pre-processed before parsing. The . INCLUDE/. LIb statements, which are SPICE commands, are not understood by the C preprocessor and so will not be pre-processed.

The \#include directive can only be used when the -E/-EE flags are specified.
Note: The C pre-processor analyses files independently. Therefore \#define statements are only known to the file they are defined in.

The -define flag can also be specified on the command line, and it will have the same effect as without the -E/-EE flags. To use \#define in Eldo in the same way you define macros in the C language, the syntax is as follows:

```
#define macro(args) expression
```

When the macro is encountered in the netlist, it is replaced by the expression. Arguments of the macro will be replaced by the literals in the macro call. For example:

```
#define sat_margin(device) abs(vds(device)-vdss(device))
.extract sat_margin(XM0.M1)
```

will be replaced by:

```
.extract abs(vds(XM0.M1)-vdss(XM0.M1))
```



## Note

Because -E/-EE uses the C pre-processor, you must ensure that there is a carriage return proceeding the directive in the file to avoid problems. Uppercase function names are not accepted. Using comments defined with \#com and \#endcom are not compatible with -E/-EE.

## Arithmetic Functions

A set of arithmetic functions may be used in Eldo for the calculation of device parameters, model parameters, new waves, and so on. These are listed below:

Table 3-2. Arithmetic Functions and Operators

| Function | Returns |
| :---: | :---: |
| SQRT(VAL) | Square root of VAL |
| LOG(VAL) | Neperian logarithm of VAL |
| LOG10(VAL) | Decimal logarithm of VAL |
| DB(VAL) | Value in dBs of VAL $\left(20 \times \log _{10}\right.$ (VAL) $)$ |
| EXP(VAL) | Exponent of VAL |
| COS(VAL) | Cosine of VAL, where VAL is defined in radians |
| SIN(VAL) | Sine of VAL, where VAL is defined in radians |
| TAN(VAL) | Tangent of VAL, where VAL is defined in radians |
| ACOS(VAL) | Arc cosine of VAL |
| ASIN(VAL) | Arc sine of VAL |
| ATAN(VAL) | Arc tangent of VAL |
| COSH(VAL) | Hyperbolic cosine of VAL |
| SINH(VAL) | Hyperbolic sine of VAL |
| TANH(VAL) | Hyperbolic tangent of VAL |
| SGN(VAL) | Returns the signum of val: +1 if val $>0,0$ if VAL $=0,-1$ if val $<0$ |
| SIGN(VAL) | Returns the signum of VAL: +1 if VAL $>=0,-1$ if VAL< 0 |
| SIGN(VAL1, VAL2) | Returns ABS (VAL1) $\times$ SGN (VAL2) |
| PWR(VAL1, VAL2) | Returns the absolute value of VAL1, raised to the power of VAL2, with the sign of VAL1 |
| POW(VAL1, VAL2) | Returns the value of VAL1 to the power of the integer part of VAL2 |
| ABS(VAL) | Absolute value of VAL: \|VAL| |
| INT(VAL) | Integer value of VAL (equivalent to TRUNC) |

Table 3-2. Arithmetic Functions and Operators

| Function | Returns |
| :---: | :---: |
| TRUNC(VAL) | Truncated value of VAL (Integer part of real value) |
| ROUND(VAL) | Rounded, to the nearest integer, value of VAL |
| CEIL(VAL) | Ceiling rounding function, returns the smallest integer value not less than VAL. This is known as rounding up. For example ceil(1.25) returns 2.0 and ceil(-1.25) return -1.0. |
| FLOOR(VAL) | Floor rounding function, returns the largest integer value not greater than VAL. This is known as rounding down. For example floor(1.25) returns 1.0 and floor(-1.25) return -2.0. |
| $\begin{aligned} & \text { MIN(VAL1,..., VALn) } \\ & \text { DMIN(VAL1,...,VALn) } \end{aligned}$ | Returns the minimum of VAL1 to VALn. There is no limit to the number of values that can be specified |
| $\begin{aligned} & \text { MAX(VAL1,..., VALn) } \\ & \text { DMAX(VAL1,...,VALn) } \end{aligned}$ | Returns the maximum of VAL1 to VALn. There is no limit to the number of values that can be specified |
| DERIV(VAL) | Returns the derivative of VAL |
| REAL) | Returns the real part of a complex number |
| IMAG() | Returns the imaginary part of a complex number |
| MAGNITUDE() | Returns the magnitude of a complex number |
| CONJ() | Returns the conjugate of a complex number |
| COMPLEX (a, b) | Returns a complex number using ' $a$ ' as the real part and ' $b$ ' as the imaginary part |
| STOSMITH(val) | Returns a normalized value of a complex quantity. These functions |
| YTOSMITH(val) | can be used to convert complex functions (S/Y/Z parameters |
| ZTOSMITH(val) | a Smith chart; an example is given in the .PLOT section of the Simulator Commands chapter. |
| DDT(VAL) | Returns the derivative of VAL |
| IDT(VAL) | Returns the integral of VAL |
| LIMIT(a, b, c) | Returns b if $\mathrm{a}<\mathrm{b}$, returns c if $\mathrm{a}>\mathrm{c}$, returns a otherwise |
| BITOF(a, b) | Returns " 1 " if bit b of the integer value of parameter a is a " 1 ". <br> Returns " 0 " if bit b of the integer value of parameter a is a " 0 " |
| $\begin{aligned} & \text { PWL(xvalue, interp, x1, y1, } \\ & \text {... xn, yn) } \end{aligned}$ | Returns the equivalent output value at the input value xvalue, interp=0\|1 specifies whether the $y$ value is interpolated linearly (1) or not (0). xn and yn are used to calculate the equivalent output value |

Table 3-2. Arithmetic Functions and Operators

| Function | Returns |
| :---: | :---: |
| PWL_CTE(xvalue, interp, $\mathrm{x} 1, \mathrm{y} 1, \ldots \mathrm{xn}, \mathrm{yn})$ | Returns the equivalent output value at the input value xvalue, interp=0\|1 specifies whether the $y$ value is interpolated linearly (1) or not (0). xn and yn are used to calculate the equivalent output value. This function plots all specified points but will hold the first specified value if the simulation start time is less than the first time point specified in the function. Similarly it will hold the last value until the simulation is complete. |
| PWL_LIN(xvalue, interp, $\mathrm{x} 1, \mathrm{y} 1, \ldots \mathrm{xn}, \mathrm{yn})$ | Returns the equivalent output value at the input value xvalue, interp=0\|1 specifies whether the $y$ value is interpolated linearly (1) or not (0). xn and yn are used to calculate the equivalent output value. This function linearly extrapolates the first value using the first two points of the function. The last value will also be linearly extrapolated using the last two points. This will only happen if the simulation start time is less than the first time value specified in the function, and the simulation end time is greater than the last time value of the function. |
| ONGRID([offset], step, value) | Returns 1 if value $=$ offset $+k \times$ step where $k$ is an integer value. Otherwise it returns 0 . Default value of offset is 0.0 . |
| SELECT(table_name, xvalue [, LINEĀR \| SAMPLE_HOLD |SPLINE]) | Returns a value interpolated from an array of ( $x, y$ ) values according to a given $x$ value. table_name is the name of an array of ( $\mathrm{x}, \mathrm{y}$ ) values defined with a . TABLe command, xvalue is the x value for which $y$ is requested, LINEAR \| SAMPLE_HOLD | SPLINE indicates the interpolation method to use to calculate the $y$ value. The default is SAMPLE_HOLD. |
| SMMIN(a, b, eps) | Returns the minimum of $a$ and $b$, with smoothing coefficient eps |
| SMMAX (a, b, eps) | Returns the maximum of a and b, with smoothing coefficient eps |
| SMABS(val, eps) | Returns the absolute value of val, with smoothing coefficient eps |
| SMSGN(val, eps) | Returns the signum of val, with smoothing coefficient eps |
| SMSIGN(val, eps) | Returns the signum of val, with smoothing coefficient eps |
| SIGMA) | Returns the sum of various items (numbers, parameters, or output quantities); wildcards are accepted for output quantities |
| MOD(x,y) | Modulo operator. Floating-point remainder value function of dividing x by y . Returns the value $\mathrm{x}-i \times \mathrm{y}$, where $i$ is the quotient of $x / y$, rounded towards zero to an integer. An error is returned if y is 0 . |

## Notes

- Where VAL is written above, it normally means a numeric value, but in certain cases, the functions may also be applied to waves.
- The max and min functions are automatically converted into dMAX and dMIn functions when necessary, for example:
R1 $12\{\min (2,1,5)\}$ is equivalent to:
R1 $12\{\operatorname{dmin}(2,1,5)\}$ which is also equivalent to:
R1 121
There is no limit to the number of arguments that can be used in max, min, dmax and DMIN arguments.
- If three arguments are specified for mIn (that is, MIN $(a, b, c)$ ), this represents the mIn of waveform $a$ in the time window $[b, c]$. Use DMIN to return the minimum of $a, b$ and $c$ as computed at each time step.
- The min/max/abs/sGn/sign functions, when used in bias-dependent expression (such as in $R(V)$ ), can cause non-convergence due to these operators making the function nonderivable. Use option "MMSMOOTH" on page 980 to make them derivable, to avoid such problems. Alternatively use the SMMIN, SMMAX, SMABS, SMSGN and SMSIGN operators.
- The functions real, imag, magnitude, cons, and complex can only be used in .EXTRACT and .DEFWAVE expressions.
- dDt (VAL) and Idt (VAL) can only be used on E \& G elements, see the corresponding descriptions for the "Voltage Controlled Voltage Source" on page 350 and "Voltage Controlled Current Source" on page 363. Expressions associated with R/L/C devices do not support DDT/IDT operators.
The DDT operator differs from the deriv operator in the sense that dDt utilizes the integration scheme used by Eldo, while the DERIv operator exclusively uses the Backward-Euler algorithm.
- There can be differences between the deriv operator of Eldo and the equivalent operator (DRV) of EZwave. The formula used for the Eldo DERIV operator is BackwardEuler $($ that is, $\operatorname{deriv}(\mathrm{f}(\mathrm{t}))=(\mathrm{f}(\mathrm{t})-\mathrm{f}(\mathrm{t}-\mathrm{h})) / \mathrm{h})$ with $t$ being the current time and $h$ being the time step, however the DRV operator of EZwave uses a more complex formula based on $\mathrm{f}(\mathrm{t}), \mathrm{f}(\mathrm{t}-\mathrm{h})$ and $\mathrm{f}(\mathrm{t}+\mathrm{h})$. Eldo cannot use the EZwave "post-processor" formulation, because it requires to know the value at $t+h$, which is not possible when the simulator is running (Eldo at time $t$ cannot know the value at $t+h$ ), but post-processor formulation is usually smoother, hence both formulations are used.
- Nested complex() statements are forbidden, as well as using complex quantities for the real or imaginary part. Corresponding errors are:

```
ERROR 3040: Nested complex(,) functions is not allowed.
ERROR 3041: Complex quantities can not be used inside complex(,) function.
```

- If Ceil, round, floor cause convergence problems, Eldo will generate a warning and invite the user to specify option noltedisc to bypass LTE checks.


## -compat Flag

When the -compat flag is active, the following arithmetic function/operator rules apply:

- $\quad \log (x)=\operatorname{sign}(x) \times \log (\operatorname{abs}(x))$
- $\log 10(x)=\operatorname{sign}(x) \times \log 10(\operatorname{abs}(x))$
- $\mathrm{db}(\mathrm{x})=\operatorname{sign}(\mathrm{x}) \times 20.0 \times \log 10 \times \operatorname{abs}(\mathrm{x}))$
- $\quad \operatorname{sqrt}(\mathrm{x})$ is $-\operatorname{sqrt}(\operatorname{abs}(\mathrm{x}))$ if x is negative.
- $x^{* *} y$ is computed as $x^{y}$ if $x$ is positive, $-\left(\operatorname{abs}(x)^{y}\right)$ if $x$ is negative, and 0 if $x$ is 0 .
- The power operator ( $\wedge$ ) has highest precedence (same as standard Eldo); prior to v6.3_2 it had lower precedence in -compat mode than the multiplication and division operators.

Note
In Eldo standard mode: $\operatorname{sqrt}(\mathrm{x})$ returns an error if x is negative; $\mathrm{x}^{* *} \mathrm{y}$ is computed as $\exp (\mathrm{y} \times \log (\mathrm{x}))$ if x is strictly positive, 0 if x is 0 , and returns an error if x is negative.

## Operators

## Operator Precedence

The order of precedence and associativity of operators in Eldo affect the evaluation of expressions. For example, in the expression $a=2+b * 3$, which happens first? the addition or the multiplication? Expressions with higher-precedence operators are evaluated first.

Table 3-3 summarizes the precedence and associativity (the order in which the operands are evaluated) of Eldo operators, listing them in order of precedence from highest to lowest. Where several operators appear together, they have equal precedence and are evaluated according to their associativity.

Table 3-3. Operator Precedence

| Operator | Description | Associativity |
| :--- | :--- | :--- |
| () | function call | left-to-right |
| $!-$ | logical NOT, unary negation | right-to-left |
| $* * \wedge$ | power, power (synonym) | left-to-right |
| $* /$ | multiply, divide | left-to-right |
| +- | add, subtract | left-to-right |
| $\langle<\rangle>$ | bitwise left shift, bitwise right shift | left-to-right |

Table 3-3. Operator Precedence

| Operator | Description | Associativity |
| :--- | :--- | :--- |
| $\langle<=\gg=$ | less than, less than or equal, greater than, <br> greater than or equal | left-to-right |
| $==!=$ | equal, not equal | left-to-right |
| $\&$ | bitwise AND | left-to-right |
| $\\|$ | bitwise OR | left-to-right |
| $\& \&$ | logical AND | left-to-right |
| $\\|$ | logical OR | left-to-right |

## Arithmetic Operators

The arithmetic operators available are,,$+- *$, and ^ (or **) for power.

## Note

$\square$ The power operator ( $\wedge$ ) has the highest precedence. For example:
$1+4^{\wedge} 2$ gives the result: 17
$2 * 3 \wedge 2$ gives the result: 18
$x^{\wedge} y$ or $x^{* *} y$ is computed as $\exp \left(y^{*} \log (x)\right)$ if $x$ is strictly positive, 0 if $x=0$, and returns an error if $x$ is negative. Specify option POwnego to allow a negative $x$ value in power expressions: the expression will return 0 . In versions of Eldo prior to v6.6, a negative $x$ value was allowed.

## Boolean Operators

The following boolean expressions/operators are available:
Table 3-4. Boolean Operators

| Operator | Meaning |
| :--- | :--- |
| $!=$ | not equal to |
| $==$ | equal to |
| $<$ | less than |
| $<=$ | less than or equal to |
| $>$ | greater than |
| $>=$ | greater than or equal to |
| $\\|$ | OR operator |
| $\dot{\alpha}=$ | AND operator |

## Bitwise Operators

The following Bitwise operators are available:
Table 3-5. Bitwise Operators

| Operator | Meaning |
| :--- | :--- |
| $\&$ | Bitwise AND operator |
| $l$ | Bitwise OR operator |
| $\ll$ | Bitwise shift left operator |
| $\gg$ | Bitwise shift right operator |

## Expressions

Expressions can be used in a netlist with certain restrictions.
Numerical expressions must be contained within braces, \{ and \}, single quotes, ' and ', or parentheses, ( and ).

String expressions should be contained in double quotes, " and ".
Mathematical grouping within expressions must be done using normal brackets, ( and ).
Constants and parameters may be used in expressions, together with the built-in functions and operators described above.

Expressions may be used in the following situations:

- Parameters in the calculation of MOS geometries and $\mathrm{R}, \mathrm{C}$ and L values.
- Parameter values in the .model command.
- Time point values in the signal descriptions pulse, pwl, SFFM, SIn and exp.
- Parameters values in the . sigbus command.
- Voltage and current source values.
- $\quad S$ and $Z$ transform ( $F N S$ and $\operatorname{FNZ}$ ) devices.
- .PARAM, .EXTRACT and .DEFWAVE commands.
- $\mathbf{E}$ and $\mathbf{G}$ sources described by functions or tables.
- $\mathbf{R}, \mathbf{C}$ and $\mathbf{L}$ devices described by functions.
i Some parameters may appear in expressions but will cause an error if used in a .PARAM command. For more information on these see "Reserved Keywords" on page 72.


## Examples

```
r1 1 2 {3.0*p1-4k}
.model nn nmos vtO={p2-p2/2.0}
e1 1 2 value={15v*sqrt (v(3,2))}
.defwave pow=v(a)*i(b)
.param x1={2*sqrt(a)}
```


## -compat flag

In -compat mode, double quotes are considered as single quotes. (In standard Eldo mode, double quotes are used to specify a parameter string.)

## Conditional Evaluation of Expressions

Parameters or source values can be evaluated in expressions containing conditional statements.

## Syntax

VALIF (CONDITION, expression1, expression2)
EVAL (CONDITION?expression1:expression2)
If condition is TRUE, then Valif (or eval) returns expression1 else it returns expression2. The keyword valif (or eval) can be used in any expression. The valif operator also accepts strings in .PARAM statements. This is useful for selecting models according to parameter values.

## Examples

$$
\begin{aligned}
& \text {.param p1 }=1.0 \\
& \text {.param p2 }=2.0 \\
& \text {.param p3 }=\text { valif }(p 1>p 2, p 1+1.5, p 2+1.5)
\end{aligned}
$$

Here, P3 will be assigned the value 3.5.

```
.param p1 =1
.param p2 = 2
.param pu = valif(p1 > p2,"r1","r2")
.model r1 r r = 1
.model r2 r r = 2
i1 1 0 1
r1 1 0 $(pu) 1
```

This examples shows the use of strings. Here, model r 2 will be used because condition $\mathrm{p} 1>\mathrm{p} 2$ is false.

## Note

The eval syntax is closer to ' C ' language, and may be more convenient for some users.

## Simulation Counters

After a simulation has been completed, Eldo writes simulation information, in tabular form, to the ASCII output (.chi) file. The following information is output:

## Node and Element Information

Information concerning circuit nodes and elements is written to the .chi file in the following format:

```
NUNODS NCNODS NUMNOD NUMEL DIODES BJT JFET MOSFET
\begin{tabular}{llllllll}
16 & 16 & 16 & 22 & 0 & 0 & 0 & 19
\end{tabular}
```

where the parameters have the following definitions:
NUNODS $\quad$ Number of nodes before subcircuit expansion. Corresponds to the number of top nodes, intrinsic nodes of devices not included.

NCNODS Number of nodes after subcircuit expansion.
NUMNOD Total number of nodes including those created by parasitic resistances.
NUMEL Total number of elements contained in the circuit.
DIODES Number of diode elements contained in the circuit.
BJT Number of BJT elements contained in the circuit.
JFET Number of JFET elements contained in the circuit.
MOSFET Number of MOSFET transistor elements contained in the circuit.

## Grounded Capacitors Information

Information concerning grounded capacitors is written to the .chi file in the following format:

```
NUMGC
1
```

where the parameters have the following definitions:
NUMGC $\quad$ Number of grounded capacitors not taken into account by NUMEL

## Matrix Information

When Eldo creates a matrix, the following information is written to the .chi file:

```
NSTOP NTERM PERSPA
    13 122 7.219e+01
```

where the parameters have the following definitions:

| NSTOP | Number of lines in the matrix |
| :--- | :--- |
| NTERM | Number of terms in the matrix |
| PERSPA | Sparsity coefficient in percent (\%) |

## Newton Block Information

When Eldo creates a number of Newton blocks, the following information is written to the .chi file:

NBLOCKS NODEBLK MAXSIZE MINSIZE
where the parameters have the following definitions:
nblocks Total number of Newton blocks created
nodeblk Number of nodes contained in each Newton block
MAXSIZE $\quad$ Size of the biggest Newton block
minsize $\quad$ Size of the smallest Newton block

## Convergence Information

Information concerning circuit nodes and elements is written to the .chi file in the following format:

| NUMTTP | NUMRTP | LTERTP | INWCALL | ITERNW | MEMSIZE |
| :--- | :--- | :--- | :--- | :--- | :--- |
| 80 | 15 | 2 | 243 | $2.000 \mathrm{e}+00$ | 581896 |

where the parameters have the following definitions:
NUMTTP Number of steps accepted by the simulator and sent to the binary output (. $w d b$ ) file

NUMRTP Number of steps rejected due to the truncation error being too large
LTERTP $\quad$ Number of time steps rejected due to LTE
INWCALL Total number of iterations or Newton calls needed to solve the Newton blocks

Total number of Newton calls for .OP, .DC and . AC analyses and is the average number of Newton calls needed to achieve convergence for a .TRAN analysis

Memory size allocated to the circuit by Eldo

| NDEVCALL | NKIRCH | NMAXCALL | ITERM | LATENCY |
| :--- | :--- | :--- | :--- | :--- |
| 16038 | 0 | 9 | $1.00 \mathrm{e}+00$ | $5.208 \mathrm{e}+00 \%$ |

where the parameters have the following definitions:

NDEVCALL Number of device calls
NKIRCH $\quad$ Number of calls or iterations needed to solve Kirchoff's Law (OSR only)
NMAXCALL Maximum number of calls needed to solve a time or DC point
ITERM Average number of OSR loops
LATENCY Percentage of latency in the circuit

## Temperature Handling

Eldo allows temperature handling using the commands .TEMP, TNOM, TMOD and $\mathbf{T}$ and allows formulation of temperature dependent functions using the variable temper (or temp). These commands and functions are briefly described below:

The тNOM function from the .OPTION command is used to set the nominal simulation temperature, that is, the temperature at which parameter calculations are made. Default is $27^{\circ} \mathrm{C}$.

## Note

TNOM may appear in expressions.
TNOM is a reserved keyword, however it may be specified as a parameter in a .PARAM command when . option defptnom is set. The temperature value used by the Eldo model evaluator is always that which is set with .OPTION TNOM=val. See "DEFPTNOM" on page 976 and "TNOM=VAL" on page 983.

The .TEMP command is used to execute several successive simulations at various temperatures. See ".TEMP" on page 907.

The тмоD parameter (in certain models) is used to set the model temperature. The value of this parameter overrides the .TEMP command above. The $\boldsymbol{T}$ parameter (in certain devices) is used to set the temperature of an individual instance of a device or model. This parameter overrides the тмоD command above.

To summarize, the order of priority of the above temperature related commands and parameters is $\boldsymbol{T}$, then $\mathbf{T M O D}$ and then . TEMP, with decreasing priority. That is, $\boldsymbol{T}$ has the highest priority.

TEMPER is a variable returned by the simulator which gives the value of the current simulation temperature and may be used in subsequent calculations. This variable will be the present simulation temperature resulting from either a .TEMP command, a .DC тemp sweep or, if neither are specified, the value of tNOM given in the . OPtion command. The temper variable may be used in the formulation of temperature dependent expressions. Any expressions containing the temper variable will be automatically reevaluated in the case of a change in this temperature.

## Note

The temp variable is synonymous with the temper variable. Both refer to the temperature of the circuit.

## Example

The temper variable may be used in conjunction with VALUE=\{EXPR\} in resistors, capacitors and inductors to specify devices whose values vary with temperature.
(i) Refer to these components in the Device Models chapter.

Cvariable 37 VALUE=\{C0*(1+0.002*(TEMPER^2)) \}
This specifies a capacitor Cvariable connected between nodes 3 and 7 and its value defined as the nominal capacitance co multiplied by ( $1+0.002$ multiplied by the square of the current simulation temperature TEMPER). The TEMPER variable may also be used in expressions for model parameters.

## Devices

## Resistor

```
Rxx N1 N2 [MOD[EL]=MNAME] [VAL] [[TC1=]T1] [[TC2=]T2] [[TC3=]T3]
+ [AC=VAL|{EXPR}] [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [L=VAL] [W=VAL]
+ [STATISTICAL=0|1] [KEEPRMIN] [NONOISE] [KF=VAL] [AF=VAL] [WEEXP=VAL]
+ [LEEXP=VAL] [FEXP=VAL] [FMIN=VAL] [FMAX=VAL] [NBF=VAL]
Rxx N1 N2 [MOD[EL]=MNAME] VALUE={EXPR} [ACDERFUNC=0|1]
+ [RESTORE_CAUSALITY=0|1] [[TC1=]T1] [[TC2=]T2] [[TC3=]T3] [AC=VAL]
+ [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [STATISTICAL=0|1] [KEEPRMIN] [NONOISE]
```

```
+ [KF=VAL] [AF=VAL] [WEEXP=VAL] [LEEXP=VAL] [FEXP=VAL] [FMIN=VAL]
+ [FMAX=VAL] [NBF=VAL] [FIT=0|1] [CFMAX=VAL] [CDELF=VAL]
Rxx N1 N2 [[TC1=]T1] [[TC2=]T2] [[TC3=]T3] [AC=VAL] [T[EMP]=VAL]
+ [DTEMP=VAL] [M=VAL] [KF=VAL] [AF=VAL] [WEEXP=VAL] [LEEXP=VAL]
+ [FEXP=VAL] [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]
+ TABLE EXPR [KEEPRMIN] [NONOISE]
Rxx NP NN POLY VAL {COEF} [TC1=T1] [TC2=T2] [TC3=T3] [STATISTICAL=0|1]
```


## Capacitor

```
Cxx NP NN [MOD[EL]=MNAME] [DCCUT] [VAL] [M=VAL] [L=VAL] [W=VAL]
+ [T[EMP]=VAL] [DTEMP=VAL] [TC1=T1] [TC2=T2] [TC3=T3] [IC=VAL]
+ [STATISTICAL=0|1]
Cxx NP NN POLY VAL {COEF} [TC1=T1] [TC2=T2] [TC3=T3] [M=VAL]
+ [CTYPE=VAL] [IC=VAL] [STATISTICAL=0 1]
CXx NP NN [VALUE=]{EXPR} [ACDERFUNC=0|1] [RESTORE_CAUSALITY=0|1]
+ [TC1=T1] [TC2=T2] [TC3=T3] [CTYPE=VAL] [STATISTICAL=0|1]
```


## Inductor

Lxx NP NN [MOD[EL]=MNAME] [DCFEED] [VAL] [M=VAL1] [T[EMP]=VAL] [DTEMP=VAL]

+ [IC=VAL3] [TC1=T1] [TC2=T2] [TC3=T3] [R=VAL4] [STATISTICAL=0|1]
Lxx NP NN POLY VAL \{LN\} [IC=VAL] [R=VAL] [TC1=T1] [TC2=T2] [TC3=T3]
+ [STATISTICAL=0|1]
Lxx NP NN [VALUE=] \{EXPR\} [ACDERFUNC=0|1] [RESTORE_CAUSALITY=0|1]
$+[\mathbf{R}=\mathrm{VAL} \mid \mathbf{R}$ VALUE=EXPR $\mid \mathbf{R}$
+ TABLE \{fval rval\}] [TC1=T1] [TC2=T2] [TC3=T3] [STATISTICAL=0|1]
Lxx \{port_list\} KMATRIX=data_block [STATISTICAL=0|1]
Lxx \{port_list\} RELUCTANCE=(\{rn, cn, valn\}) <options> [STATISTICAL=0|1]
Lxx \{port_list\} RELUCTANCE \{FILE="file"\} <options> [STATISTICAL=0|1]


## Coupled Inductor

Kxx Lyy Lzz KVAL [KR=KRVAL]

## RC Wire

```
Rxx N1 N2 MNAME [[R=]VAL] [TC1=VAL] [TC2=VAL] [C=VAL] [CRATIO=VAL]
+ [L=VAL] [W=VAL] [M=VAL] [T[EMP]=VAL] [DTEMP=VAL] [SCALE=VAL]
+ [STATISTICAL=0|1]
```


## Diffusion Resistor

```
Pxx N1 N2 [NS] MNAME [L=VAL] [W=VAL] [NB=VAL]
```


## Semiconductor Resistor

Pxx N1 N2 NS MNAME [R=VAL] [L=VAL] [CL=VAL] [W=VAL] [CW=VAL] [AREA=VAL] $+[$ STATISTICAL $=0 \mid 1]$

## Transmission Line

```
Txx NAP NAN NBP NBN [ZO=VAL1] TD=VAL2 [STATISTICAL=0|1]
Txx NAP NAN NBP NBN [\mathbf{ZO=VAL1] F=VAL3 [NL=VAL4] [STATISTICAL=0|1]}
```


## Lossy Transmission Line

Yxx LDTL [PIN:] P1...PN [REFin] PN+1...P2N REFout

+ [PARAM:] [LEVEL=val] [LENGTH=val] [SAVEFIT=val] [M=val]


## Lossy Transmission Line: W Model

Wxx N=nb_line

+ P1...PN PGNDin PN+1...P2N PGNDout
+ RLGCfile=file_name L=length [FP=val]
+ [MULTIDEBYE=val] [SAVEFIT=val] [COMPAT=val] [FGD=val]


## Lossy Transmission Line: U Model

Uxx P1...PN PGNDin PN+1...P2N PGNDout UNAME L=length [SAVEFIT=val]

## MTEE—Microstrip T Junction

Yxx MTEE P1 P2 P3 P4 P5 P6 PARAM: [W1=val] [W2=val] [W3=val] + [T=val] [Er=val] [H=val]

MBEND—Microstrip Bend (Arbitrary Angle, Optimally Mitered)

```
Yxx MBEND P1 P2 P3 P4 PARAM: [W=val] [H=val] [Er=val] [T=val]
```

+ [RHO=val] [TAND=val] [M=val] [ANGLE=val]


## MBEND2-90-degree Microstrip Bend (Mitered)

Yxx MBEND2 P1 P2 P3 P4 PARAM: [H=val] [W=val] [Er=val]
MBEND3-90-degree Microstrip Bend (Optimally Mitered)

## MCORN—90-degree Microstrip Bend (Unmitered)

```
Yxx MCORN P1 P2 P3 P4 PARAM: [W=val] [H=val] [Er=val]
```


## MSTEP-Microstrip Step in Width

Yxx MSTEP P1 P2 P3 P4 PARAM: [W1=val] [W2=val] [ER=val] + [H=val] [F=val] [ASYMMETRICAL=val] [T=val]

## VIA2-Cylindrical Via Hole in Microstrip

```
Yxx VIA2 P1 P2 PARAM: [H=val] [R=val] [COND=val] [T=val] [F=val]
```


## SBEND—Unmitered Stripline Bend

```
Yxx SBEND P1 P2 P3 P4 PARAM: [W=val] [B=val] [ER=val] [T=val]
```

+ [ANGLE=val] [F=val]


## STEE—Stripline T Junction

```
Yxx STEE P1 P2 P3 P4 P4 P5 PARAM: [W1=val] [W2=val] [W3=val]
+ [B=val] [ER=val] [T=val] [F=val]
```


## SSTEP-Stripline Step in Width

```
Yxx SSTEP P1 P2 P3 P4 PARAM: [W1=val] [W2=val] [B=val] [T=val]
```

+ [ER=val] [F=val]


## Junction Diode

Dxx NP NN [NM] MNAME [ [AREA=]AREA_VAL] [PERI|PJ|PD=PERIVAL]

+ [PGATE=PGATE_VAL] [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [OFF=0|1] + [STATISTICAL=0|1] [NOISE=0|1] [NONOISE]
Dxx NP NN [NM] MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]


## BJT—Bipolar Junction Transistor

Qxx NC NB NE [NS] [TH] MNAME [[AREA=]AREA_VAL] [AREAB=AREA_VAL]
$+[$ AREAC=AREA_VAL] [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [OFF=0|1]
$+[$ STATISTICAL=0|1] [NOISE=0|1] [NONOISE]
Qxx NC NB NE [NS] MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]

## JFET—Junction Field Effect Transistor

```
Jxx ND NG NS MNAME [[AREA=]AREA_VAL] [L=VAL] [W=VAL]
+ [T[EMP]=VAL] [DTEMP=VAL] [STATISTICAL=0|1] [OFF=0|1] [NONOISE]
Jxx ND NG NS MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]
```


## MESFET—Metal Semiconductor Field Effect Transistor

Jxx ND NG NS MNAME [AREA] [L=VAL] [W=VAL] [T[EMP]=VAL] [DTEMP=VAL] + [STATISTICAL=0|1] [OFF=0|1] [NONOISE]
Jxx ND NG NS MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]

## MOSFET

```
Mxx ND NG NS [NB] [{NN}] [MOD [EL]=]MNAME [[L=]VAL] [[W=]VAL]
+ [\mathbf{AD}=VAL] [AS=VAL] [PD=VAL] [PS=VAL] [GEO=VAL] [NRD=VAL] [NRS=VAL]
+ [M=VAL] [RDC=VAL] [RSC=VAL] [T[EMP]=VAL] [DTEMP=VAL] [STATISTICAL=0|1]
+ [NONOISE]
Mxx ND NG NS [NB] [{NN}] [MOD[EL]=]MNAME [W=VAL] [L=VAL]
+ [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]
```


## S-Domain Filter

FNSxx IN OUT [RIN=val] [ROUT=val] NN \{NN\}, DN \{DN\}

## Z-Domain Filter

FNZxx IN OUT FREQ=VAL [RIN=val] [ROUT=val] NN \{NN\}, DN \{DN\}

## Subcircuit Instance

```
Xxx NN {NN} NAME [PAR=VAL] [PAR={EXPR}] [M=VAL] [TEMP=VAL]
+ [STATISTICAL=0|1] [(SWITCH|ANALOG|OSR|DIGITAL)] [NONOISE|NOISE=0]
Xxx [MODEL:] MNAME PIN: {pin=net}
+ PARAM: {par=val} KEYWORD: {keywords} [STATISTICAL=0|1]
XXX [MODEL:] MNAME NET: {net=pin}
+ PARAM: {par=val} KEYWORD: {keywords} [STATISTICAL=0|1]
```


## Sources

## Independent Voltage Source

```
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TIME_DEPENDENT_FUNCTION }\mp@subsup{}{}{1}] [TC1=val] [TC2=val]
+ [RPORT=val [NONOISE]] [RPORT_TC1=val] [RPORT_TC2=val]
+ [IPORT=val] [CPORT=val] [LPORT=val] [MODE=keyword] [NOISETEMP=val]
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TIME_DEPENDENT_FUNCTION }\mp@subsup{}{}{1}] [TC1=val] [TC2=val]
+ ZPORT_FILE=string [IPORT=val] [CPORT=val] [LPORT=val] [MODE=keyword]
+ [NOISETEMP=val]
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE [THN=VAL] [FLN=VAL]
+ [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL] [FMAX=VAL]
+ [NBF=VAL]
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE [THN=VAL] [FLN=VAL]
+ [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL] [FMAX=VAL]
+ [NBF=VAL]
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC|OCT|LIN|LOG] [DB|MA]
+ (f1 val1) (f2 val2) ...
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC|OCT|LIN|LOG] [DB|MA]
+ (f1 val1) (f2 val2) ...
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] FOUR
+ fund1 [fund2 [fund3]] MA |RI|DB|PMA |PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
```

[^0]```
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string
+ [IPORT=val] [CPORT=val] [LPORT=val] [MODE=keyword] [NOISETEMP=val] FOUR
+ fund1 [fund2 [fund3]] MA |RI|DB|PMA|PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
```


## Independent Current Source

```
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TIME_DEPENDENT_FUNCTION }\mp@subsup{}{}{1}\mathrm{ ] [TC1=val] [TC2=val]
+ [RPORT=val [NONOISE]] [RPORT_TC1=val] [RPORT_TC2=val]
+ [IPORT=val] [CPORT=val] [LPORT=val] [NOISETEMP=val]
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TIME_DEPENDENT_FUNCTION }\mp@subsup{}{}{1}\mathrm{ ] [TC1=val] [TC2=val]
+ ZPORT_FILE=string [IPORT=val] [CPORT=val] [LPORT=val] [MODE=keyword]
+ [NOISETEMP=val]
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [NOISETEMP=val] NOISE [THN=VAL] [FLN=VAL]
+ [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL] [FMAX=VAL]
+ [NBF=VAL]
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [IPORT=val] [CPORT=val]
+ ZPORT_FILE=string [LPORT=val] [MODE=keyword] [NOISETEMP=val]
+ NOISE [THN=VAL] [FLN=VAL] [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL]
+ [FMAX=VAL] [NBF=VAL]
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC|OCT |IN|LOG] (f1 val1) (f2 val2) ...
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC|OCT|LIN|LOG] (f1 val1) (f2 val2) ...
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [NOISETEMP=val] FOUR fund1 [fund2 [fund3]]
+ MA |RI|DB|PMA|PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] FOUR fund1 [fund2 [fund3]]
+ MA|RI|DB|PMA|PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
```


## Amplitude Modulation Function

AM (AMPLITUDE OFFSET FM FC TD)

1. Refer to the EXP, PULSE, PWL, SFFM and SIN source functions.

## Exponential Function

EXP (V1 V2 [TD1 [TAU1 [TD2 [TAU2]]]])

## Noise Function

NOISE THN FLN ALPHA [FC N] [FMIN] [FMAX] [NBF]

## Noise Table Function

NOISE TABLE [ [INTERP=]DEC|OCT|LIN|LOG|HARM_DEC|HARM_OCT] [DB|MA] + (f1 val1) (f2 val2) ...

## Pattern Function

PATTERN VHI VLO TDELAY TRISE TFALL TSAMPLE BITS R

## Pulse Function

PULSE (VO V1 [TD [TR [TF [PW [PER]]]]])

## Piece Wise Linear Function

```
PWL (TN VN {TN VN} [TD=val] [R=val] [SHIFT=val] [R] [SCALE=val]
+ [STRETCH=val])
PWL (FILE=<pwl_file> [TD=val] [R=val] [SHIFT=val] [R] [SCALE=val]
+ [STRETCH=val])
PWL (FILE=<pwl_file> [COL=val] [ISTEP=val] [ISTART=val] [ISTOP=val]
+ [TD=val] [R=val] [SHIFT=val] [R] [SCALE=val] [STRETCH=val])
```


## Single Frequency FM Function

SFFM (SO SA [FC [MDI [FS]]])

## Sine Function

SIN (VO VA [FR [TD [THETA [PHASE]]]])

## Trapezoidal Pulse With Bit Pattern Function

PBIT V0 V1 TD TD01 TR01 TD10 TF10 BITTIME \{PATTERN\} [R]

## Exponential Pulse With Bit Pattern Function

```
EBIT V0 V1 TD TD01 TAU01 TD10 TAU10 BITTIME {PATTERN} [R]
```


## Voltage Controlled Voltage Source

Exx NP NN [VCVS] NCP NCN VAL [MIN=VAL] [MAX=VAL]

+ [ $\mathbf{T C 1}=\mathrm{VAL}] \quad[\mathbf{T C 2}=\mathrm{VAL}] \quad[\mathbf{S C A L E}=\mathrm{VAL}] \quad[\mathbf{A B S}=\mathrm{VAL}]$
Exx NP NN [VCVS] NCP NCN VALO \{VALn\} [MIN=VAL] [MAX=VAL]
+ [ $\mathbf{T C 1}=\mathrm{VAL}]$ [ $\mathbf{T C 2}=\mathrm{VAL}]$ [SCALE=VAL] [ $\mathbf{A B S}=\mathrm{VAL}]$

```
Exx NP NN [VCVS] POLY(ND) PCP PCN {PCP PCN} PN {PN}
+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Exx NP NN PWL(1) NCP NCN PWL_LIST [DELTA=val]
+ [\mathbf{TC1}=\textrm{VAL}] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Exx NP NN NAND (ND)|AND (ND)|OR(ND)|NOR(ND) PCP PCN {PCP PCN}
+ PWL_LIST [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Exx NP NN DELAY NCP NCN [TD=val] [ABS=VAL]
Exx NP NN VALUE={EXPR} [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Exx NP NN [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL]
+ TABLE EXPR=(XN YN) {(XN YN)} [ABS=VAL]
Exx NP NN INTEGRATION|DERIVATION NCP NCN VAL
+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Exx NP NN FNS NCP NCN n0 n1 ... nm, p0 p1 ... pn
Exx NP NN PZ NCP NCN a zr1 zil ... zrm zim, b prl pil ... prn pin
Exx NP NN FREQ NCP NCN f0 a0 ph0 f1 al ph1... fn an phn
+ [RESTORE_CAUSALITY=val]
Exx NP NN TRANS[FORMER] NCP NCN VAL [MIN=VAL] [MAX=VAL]
+ [\mathbf{TC1}=\textrm{VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]}
Exx NP NN OPAMP NCP NCN
```


## Current Controlled Current Source

```
Fxx NP NN [CCCS] VN VAL [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Fxx NP NN [CCCS] POLY(N) VN {VN} PN {PN}
+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Fxx NP NN PWL(1) VN PWL_LIST [DELTA=val]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Fxx NP NN NAND (ND) AND (ND)|OR(ND) NOR(ND) VN {VN}
+ PWL_LIST [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Fxx NP NN DELAY VN [TD=val] [ABS=VAL]
Fxx NP NN INTEGRATION|DERIVATION VN VAL [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
```


## Voltage Controlled Current Source

```
Gxx NP NN [VCR|VCCAP|VCCS]] NCP NCN VAL [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Gxx NP NN [VCR|VCCAP|VCCS] POLY(ND) PCP PCN {PCP PCN} PN {PN}
+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Gxx NP NN VCR [PWL(1)|NPWL(1)|PPWL(1)] NCP NCN PWL_LIST
+ [DELTA=val] [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL]
+ [SCALE=VAL] [ABS=VAL]
Gxx NP NN NAND (ND)|AND (ND)|OR(ND)|NOR(ND) PCP PCN {PCP PCN}
+ PWL_LIST [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Gxx NP NN DELAY NCP NCN [TD=val] [ABS=VAL]
Gxx NP NN VALUE={EXPR} [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Gxx NP NN [VCR|VCCAP|VCCS] [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL]
+ [SCALE=VAL] [ABS=VAL] TABLE EXPR=(XN YN) {(XN YN)}
Gxx NP NN INTEGRATION|DERIVATION NCP NCN VAL
+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Gxx NP NN FREQ NCP NCN f0 a0 ph0 f1 al ph1... fn an phn
+ [RESTORE_CAUSALITY=val]
```


## Current Controlled Voltage Source

```
Hxx NP NN [CCVS] VN VAL [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Hxx NP NN [CCVS] POLY(N) VN {VN} PN {PN}
+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Hxx NP NN PWL(1) VN PWL_LIST [DELTA=val]
+ [\mathbf{TC1}=\textrm{VAL}] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Hxx NP NN NAND (ND)|AND (ND)|OR(ND)|NOR(ND) VN {VN}
+ PWL_LIST [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Hxx NP NN DELAY VN [TD=val] [ABS=VAL]
Hxx NP NN INTEGRATION|DERIVATION VN VAL [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
```


## S, Y, Z Parameter Extraction

VYy NP NN IPORT=VAL [RPORT=VAL] [CPORT=VAL] [LPORT=VAL] [MODE=KEYWORD] VYy NP NN IPORT=VAL ZPORT_FILE=string [CPORT=VAL] [LPORT=VAL] + [MODE=KEYWORD]
IYY NP NN IPORT=VAL [RPORT=VAL] [CPORT=VAL] [LPORT=VAL] [MODE=KEYWORD] IYy NP NN IPORT=VAL ZPORT_FILE=string [CPORT=VAL] [LPORT=VAL] + [MODE=KEYWORD]

## Macromodels

## Analog

## Comparator

COMPxx INP INN OUT [MNAME] [VHI=VAL1] [VLO=VAL2]

+ [VOFF=VAL3] [VDEF=VAL4] [TCOM=VAL5] [TPD=VAL6]
COMPDxx INP INN OUTP OUTN [MNAME] [VHI=VAL1] [VLO=VAL2]
+ [VOFF=VAL3] [VDEF=VAL4] [TCOM=VAL5] [TPD=VAL6]


## Op-amp (Linear)

Yxx OPAMPO [PIN:] INP INN OUT AGND

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
YXX OPAMPOD [PIN:] INP INN OUTN OUTP AGND
+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Op-amp (Linear 1-pole)

```
Yxx OPAMP1 [PIN:] INP INN OUT AGND
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
Yxx OPAMP1D [PIN:] INP INN OUTN OUTP AGND
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```


## Op-amp (Linear 2-pole)

```
YXX OPAMP2 [PIN:] INP INN OUT AGND
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

YXX OPAMP2D [PIN:] INP INN OUTN OUTP AGND

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Delay

DELXx IN OUT VAL

## Saturating Resistor

YXX SATR [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Voltage Limiter

Yxx SATV [PIN:] INP INN OUTP OUTN

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Current Limiter

Yxx SATI [PIN:] IN OUT

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Voltage Controlled Switch

Yxx VSWITCH [PIN:] NP NN CP CN [PARAM: PAR=VAL \{PAR=VAL\}] MODEL: MNAME

## Current Controlled Switch

Yxx CSWITCH [PIN:] NP NN IC: VNAME

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Triangular to Sine Wave Converter

Yxx TRI2SIN [PIN:] INP INN OUTP OUTN

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Staircase Waveform Generator

Yxx STAIRGEN [PIN:] NP NN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Sawtooth Waveform Generator

YXX SAWGEN [PIN:] NP NN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Triangular Waveform Generator

YXx TRIGEN [PIN:] NP NN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Amplitude Modulator

YXx AMM [PIN:] INP INN OUTP OUTN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Pulse Amplitude Modulator

YXx PAM [PIN:] INP INN OUTP OUTN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Sample and Hold

YXX SA_HO [PIN:] INP INN OUTP OUTN

+ [PARAM: PAR=VAL $\{P A R=V A L\}] \quad$ [MODEL: MNAME]


## Track and Hold

YXX TR_HO [PIN:] INP INN OUTP OUTN CRT

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Pulse Width Modulator

YXx PWM [PIN:] CTRP CTRN OUTP OUTN

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Voltage Controlled Oscillator

Yxx VCO [PIN:] INP INN OUTP OUTN

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Peak Detector

```
Yxx PEAK_D [PIN:] INP INN OUTP OUTN CRT
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```


## Level Detector

```
Yxx LEV_D [PIN:] INP INN OUTP OUTN
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
Yxx LEV_D [PIN:] INP INN OUTP OUTN REF
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```


## Logarithmic Amplifier

Yxx LOGAMP [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Anti-logarithmic Amplifier

YXX EXPAMP [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Differentiator

YXX DIFF [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Integrator

Yxx INTEG [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Adder, Subtractor, Multiplier and Divider

```
Yxx ADD [PIN:] IN1 IN2 OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
Yxx SUB [PIN:] IN1 IN2 OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
YXx MULT [PIN:] IN1 IN2 OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
Yxx DIV [PIN:] IN1 IN2 OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```


## Digital

## Digital Model Definition

```
.MODEL MNAME LOGIC [VHI=VAL1] [VLO=VAL2] [VTH=VAL3]
+ [VTHI=VAL4] [VTLO=VAL5] [TPD=VAL6] [TPDUP=VAL7]
+ [TPDOWN=VAL8] [CIN=VAL9] [DRVL=VAL10] [DRVH=VAL11]
```


## Delay

DELxx IN OUT VAL

## Inverter

```
INVxx IN OUT [REF1 REF2] [MNAME] [PAR=VAL]
```


## Exclusive-OR Gate

XORxx IN1 IN2 OUT [REF1 REF2] [MNAME] [PAR=VAL]

## 2-Input Digital Gates



## 3-Input Digital Gates

```
<dgate><xx> IN1 IN2 IN3 OUT [REF1 REF2] [MNAME] [PAR=VAL]
Nand NAND3xx IN1 IN2 IN3 OUT [REF1 REF2] [MNAME] [PAR=VAL]
And AND3xx IN1 IN2 IN3 OUT [REF1 REF2] [MNAME] [PAR=VAL]
Nor NOR3xx IN1 IN2 IN3 OUT [REF1 REF2] [MNAME] [PAR=VAL]
Or OR3xx IN1 IN2 IN3 OUT [REF1 REF2] [MNAME] [PAR=VAL]
```


## Multiple Input Digital Gates



## Mixed

## Analog to Digital Converter

ADCxx CLK IN OUTSB\{OUTSB\} [EDGE=VAL1] [VTH=VAL2] [VHI=VAL3]

+ [VLO=VAL4] [VINF=VAL5] [VSUP=VAL6] [TCOM=VAL7] [TPD=VAL8]


## Digital to Analog Converter

DACxx CLK INSB\{INSB\} OUT [EDGE=VAL1] [VTH=VAL2]

+ [VTIN=VAL3] [VHI=VAL4] [VLO=VAL5] [TPD=VAL6] [SL=VAL7]


## Magnetic

## Transformer Winding

Yxx WINDING [PIN:] E1 E2 M1 M2 [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Non-linear Magnetic Core 1

Yxx NLCORE1 [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Non-linear Magnetic Core 2

Yxx NLCORE2 [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Linear Magnetic Core

Yxx LINCORE [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Magnetic Air Gap

YXX AIRGAP [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Transformer (Variable \# of Windings)

Yxx LVTRANS [PIN:] P1P P1N P2P P2N \{PNP PNN\}

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Ideal Transformer

Yxx JTRAN N1 N2 N3 N4 [PARAM: A=VAL]

## Switched Capacitor

## Operational Amplifier

```
OPAxx INP INN OUTP OUTN [MNAME] [LEVEL=VAL1] [VOFF=VAL2]
+ [SL=VAL3] [CIN=VAL4] [RS=VAL5] [VSAT=VAL6] [VSATN=VAL7] [GAIN=VAL8]
+ [FC=VAL9] [FNDP=VAL10] [IMAX=VAL11] [CMRR=VAL12]
```


## Switch

Sxx NC N1 N2 [MNAME] [RON [CREC]]

## Ideal Operational Amplifier

YXx SC_IDEAL [PIN:] INP INN OUT [PARAM: M=val]

## Inverting Switched Capacitor

```
YXx SC_I [PIN:] P1 P2 N2 N1 [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```


## Non-inverting Switched Capacitor

Yxx SC_N [PIN:] P1 P2 N1 N2 [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Parallel Switched Capacitor

Yxx SC_P [PIN:] P1 P2 N [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Serial Switched Capacitor

```
Yxx SC_S1 [PIN:] IN OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
YXX SC_S2 [PIN:] IN OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```


## Serial-parallel Switched Capacitor

```
Yxx SC_SP1 [PIN:] IN OUT REF [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
Yxx SC_SP2 [PIN:] IN OUT REF [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```


## Bi-linear Switched Capacitor

Yxx SC_B [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Unswitched Capacitor

YXx SC_U [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

## Commands

## Analog-to-Digital Converter

```
.A2D [SIM=simulator] eldo_node_name
+ [digital_node_name] [MOD=model_name] [parameters_list]
```


## AC Analysis

```
.AC TYPE nb fstart fstop [SWEEP DATA=dataname] [UIC] [MONTE=val]
.AC TYPE nb fstart fstop [SWEEP parameter_name TYPE nb start stop]
+ [UIC] [MONTE=val]
.AC TYPE nb fstart fstop [SWEEP parameter_name start stop incr]
```

```
+ [UIC] [MONTE=val]
.AC DATA=dataname [SWEEP DATA=dataname] [UIC] [MONTE=val]
.AC DATA=dataname [SWEEP parameter_name TYPE nb start stop]
+ [UIC] [MONTE=val]
.AC DATA=dataname [SWEEP parameter_name start stop incr] [UIC] [MONTE=val]
.AC LIST {list_of_frequency_points}
+ [SWEEP DATA=dataname] [UIC] [MONTE=val]
.AC LIST {list_of_frequency_points}
+ [SWEEP parameter_name TYPE nb start stop] [UIC] [MONTE=val]
.AC LIST {list_of_frequency_points}
+ [SWEEP parameter_name start stop incr] [UIC] [MONTE=val]
.AC ADAPTIVE tolerance_value fstart fstop
```


## Insert a Model or Subcircuit File

.ADDLIB N DIR_NAME

## Age Analysis

```
.AGE [TAGE=value] [TUNIT=year|month|day|hour|min sec] [NBRUN[S]=value]
+ [LIN[={YES|ON| 1}|{NO|OFF|O}] | LOG[={YES |ON| 1} {NO|OFF|0}]]
+ [LOGMODE_MINEXP=value]
+ [TSTART=value] [TSTOP=value] [TWINDOW={(a1,b1) (an,bn)}]
+ [MODE= sim | load | save | MCload | blockload] [AGELIB=file_name]
+ [AGEALL[={YES ON ON}|{NO OFF O}]]
+ [RESTRICT_MC={YES|ON| 1} {NO|OFF|0}]
+ [ASCII[={YES|ON| 1}|{NO|OFF|O}]]
+ [COMPUTE_LAST[={YES|ON|1}|{NO|OFF|0}]]
+ [PLOT={FRESH_FINAL|ALL}]
+ [AGEDSIM={YES |ON | 1}|{NO|OFF|O}]
+ [PRINT_CONFIGURATION={YES|ON| 1}|{NO|OFF|0}]
+ [STRESS_LIST={YES|ON|1}|{NO|OFF|0}]
+ [STRESS_SORT_NBMAX=value]
+ [STRESS_SORT_REL=value]
+ [STRESS_SORT_ABS=value]
+ [STRESS_LIST_FILE=file_name]
+ [STRESS_LIST_SPLIT_MOS={YES|ON|1}|{NO|OFF|0}]
+ [STRESS_SORT_ORDER=ASCENDING|DESCENDING]
+ [STRESS_SORT_DELTA=extract_label]
+ [DELTA_VDS=value]
+ [DELTA_VGS=value]
+ [DELTA_VBS=value]
+ [USER_WARNING={YES|ON| 1}|{NO|OFF|0}]
```


## Define Functions For Reliability

```
.AGE_LIB
+ FILE=library_name
+ FNC_PREFIX=fnc_prefix
+ LEVEL=level1[{, level2, ..., leveln}]
+ [SHARED_PATH=yes|no]
+ [PFDIR=library_path]
```


## Reliability Model Parameter Declaration

[^1]
## Generalized Re-run Facility

.ALTER [LABEL]
[ELEMENT]
[SUBCKT]
[COMMAND]
[COMMENT]
.ALTER | .END

## Configure Spice Descriptions

```
.BIND INST=inst_name [EXCEPT=inst_name]
FROM_SUBCKT=Eldo_subckt_name | FROM_MODEL=HDL_model_name
    TO_SUBCKT=new_Eldo_subckt_name
    [FILE=<file_name> VARIANT=<variant_name>]
|O_MODEL=new_HDL_model_name
    [MAPPING=assoc_file_name | DEFAULT_MAPPING=by_name|by_position]
.BIND INST=inst_name [EXCEPT=inst_name]
        FROM_SUBCKT=Eldo_subckt_name | FROM_MODEL=HDL_model_name
        TO_SUBCKT=new_Eldo_subckt_name
        [FILE=<file_name> VARIANT=<variant_name>]
| TO_MODEL=new_HDL_model_name
    [MAPPING=assoc_file_name | DEFAULT_MAPPING=by_name|by_position]
```


## Define local scope for .BIND

```
.BINDSCOPE PATH=scope_path
```


## Call Tcl Function

```
.CALL_TCL [TRAN|AC|DC|...]
+ WHERE=START|START_OF_RUN|END_OF_RUN|END
+ [PLOT=[YES|NO|O|1]] [PLOT_TYPE=[TRAN |AC |DC | . .]]
+ [LABEL=alias_name] tcl_function_call
```


## Check Bus Values

```
.CHECKBUS BNAME [VTH[1]=VAL1] [VTH2=VAL2] [BASE=DEC|OCT|BIN|HEX] [LOCK=1]
+ [REPORTX=0|1] TN VAL {TN VAL}
.CHECKBUS BNAME [VTH[1]=VAL1 [VTH2=VAL2]] [TSAMPLE=VAL] [TDELAY=VAL]
+ [BASE=DEC|OCT|BIN|HEX] [LOCK=1] [REPORTX=0|1] PATTERN BITS {BITS}
```


## Check Safe Operating Area Limits

```
.CHECKSOA [ANALYSIS] [TSTART=val1 [TSTOP=val2]] [AUTOSTOP]
+ [NOMERGE] [NOLIB] [FILE=file_name] [NOXWINDOW]
+ [SUBCKT={list_of_subckt_instances}] [RUNTMSG]
```


## Piece Wise Linear Source

```
.CHRENT NODE TN VN {TN VN} [P|F]
.CHRENT NODE (TN VN {TN VN}) FACTN {(TN VN {TN VN}) FACTN} [P|F]
```


## Input from a Prior Simulation

```
.CHRSIM IN OUT FILE [TSTART=V1] [TSTEP=V2] [BP=0|1|2]
+ [ZOOMTIME] [FORMAT=WDB] [RUN=val] [TYPE=CURRENT|VOLTAGE]
```


## Change Comment Character

. COMCHAR char $\{$ char\}

## Connect Two Nodes

.CONNECT N1 N2

## Current Used by a Circuit

.CONSO VN \{VN\}

## Correlation between Parameters

## . CORREL [PARAM=]param_list $\mathbf{C C = V A L}$

. CORREL DEV[ICE]=device_list PARAM=param_list $\mathbf{C C}=\mathrm{VAL}$

## Digital-to-Analog Converter

```
.D2A [SIM=simulator] eldo_node_name
+ [digital_node_name] [MOD=model_name] [parameters_list]
```


## Parameter Sweep

.DATA dataname parameter_list
[+] val_list1
[+] val_list2
[+] ...
[.ENDDATA]
. DATA dataname MER[GE]|LAM[INATED]
[+] file=filename1 param=column ... param=column
[+] file=filename2 param=column ...
[+] ...
[+] [out=outfile]
[.ENDDATA]

## DC Analysis

```
.DC
.DC CNAM [L|W] [TYPE nb] START STOP INCR [SWEEP DATA=dataname] [MONTE=val]
.DC CNAM [L|W] [TYPE nb] START STOP INCR
+ [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC CNAM [L|W] [TYPE nb] START STOP INCR
+ [SWEEP parameter_name start stop incr] [MONTE=val]
.DC SNAM [TYPE nb] START STOP INCR [SNAM2 START2 STOP2 INCR2]
+ [SWEEP DATA=dataname] [MONTE=val]
.DC SNAM [TYPE nb] START STOP INCR [SNAM2 START2 STOP2 INCR2]
+ [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC SNAM [TYPE nb] START STOP INCR [SNAM2 START2 STOP2 INCR2]
```

```
+ [SWEEP parameter_name start stop] incr [MONTE=val]
.DC TEMP START STOP INCR [SWEEP DATA=dataname] [MONTE=val]
.DC TEMP START STOP INCR [SWEEP parameter_name TYPE nb start stop]
+ [MONTE=val]
.DC TEMP START STOP INCR [SWEEP parameter_name start stop incr]
+ [MONTE=val]
.DC PARAM PARAM_NAME START STOP INCR [SWEEP DATA=dataname]
+ [MONTE=val]
.DC PARAM PARAM_NAME START STOP INCR
+ [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC PARAM PARAM_NAME START STOP INCR
+ [SWEEP parameter_name start stop incr] [MONTE=val]
.DC PARAM PARAM_NAME [TYPE nb] START STOP INCR
.DC DATA=dataname [SWEEP DATA=dataname] [MONTE=val]
.DC DATA=dataname [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC DATA=dataname [SWEEP parameter_name start stop incr] [MONTE=val]
```


## DC Mismatch Analysis

```
.DCMISMATCH [output] [DCALL[=0|1]]
+ [SORT_REL=value] [SORT_ABS=value] [SORT_NBMAX=value] [NSIGMA=value]
```


## Set Default Conditions

```
.DE[FAULT] TYPE VALUE
.DE[FAULT] TYPE {KEYWORD [VALUE]}
```


## Macro Definition

.DEFMAC MAC_NAME (ARG $\{, ~ A R G\})=E X P R E S S I O N$

## Model Name Mapping

.DEFMOD alias_model_name actual_model_name

## Plotting an Analog Signal as a Digital Bus

.DEFPLOTDIG [VTH[1]=VAL1 [VTH2=VAL2]]

## Waveform Definition

```
.DEFWAVE [SWEEP] [ANALYSIS] WAVE_NAME=WAVE_EXPR
```


## Remove library name

```
.DEL LIB LIB_NAME
```


## Design of Experiments

```
.DEX
+ EXPERIMENT = SCREENING | SCREENING_CTRL | SCREENING_NOISE
+ RESPONSE = LIST_OF_MEASURES
+ [DESIGN = ORTHA_2_N | ORTHA_2_2N | FULL_FACT]
+ [FACTOR = LIST_OF_FACTORS]
```

```
+ [FIND_FACTOR]
```


## Ignore Instances or Subckt Definitions

```
.DISCARD INST | SUBCKT | DEV =(NAME, {NAME})
```


## Disable Flat Netlist Mode

```
.DISFLAT
```


## User Defined Distributions (Monte Carlo)

```
.DISTRIB DIST_NAME (DEV1 PROB1) [{(DEVn PROBn)}]
```


## DSP (Digital Signal Processing) Computation

.DSP LABEL=label_name MODEL=model_name waveform_name

## Load DSPF File

```
.DSPF_INCLUDE [FILE=]DSPF_FILENAME [INST={list_of_subckt_inst}]
+ [LEVEL=C |RC|RCC] [DEV=DSPF |SCH[EMATIC]] [RMINVAL=val] [CMINVAL=val]
+ [CCMINVAL=val] [ADDXNET] [ADDX] [MSUFFIX=string]
.DSPF_INCLUDE [FILE=]DSPF_FILENAME [LEVEL=C|RC|RCC]
+ [DEV=DSPF|SCH[EMATIC]] DEDICATEDX=subckt_name [RMINVAL=val]
+ [CMINVAL=val] [CCMINVAL=val] [ADDXNET] [ADDX] [MSUFFIX=string]
```


## PSD (Power Spectral Density) Computation

```
.DSPMOD DSP=CORRELO|PERIODO LABEL=label_name
+ [TSTART=val] [TSTOP=val] [FS=val] [NBPT=val]
+ [PADDING=val] [WINDOW=name] [ALPHA=val] [BETA=val]
+ [NORMALIZED=val] [INTERPOLATE=val] [DISPLAY_INPUT=val]
+ [FNORMAL=val] [FMIN=val] [FMAX=val]
+ [NAUTO=val] [NCORR=val] [NPSD=val] [NSECT=val]
```


## Histogram Computation

```
.DSPMOD DSP=HISTOGRAM LABEL=label_name NBINTERVAL=val
+ [XSTART=val XSTOP=val SAMPLE=YES|NO FS=val]
```


## Frequency Computation

```
.DSPMOD DSP=FREQUENCY LABEL=label_name
+ [BASELINE=val] [TOPLINE=val]
+ [EDGE_TRIGGER = RISING | FALLING | EITHER]
+ [XSTART=val] [XEND=val]
```


## End Eldo Netlist

. END

## End Eldo Library Variant Description

.ENDL

## End Eldo Subcircuit Description

.ENDS

## Replace Node Name for Display

.EQUIV new_name=netlist_name

## Extract Mode

## Extract Waveform Characteristics

```
.EXTRACT [EXTRACT_INFO] [LABEL=NAME] [FILE=FNAME] [VECT]
+ [CATVECT] $MACRO|FUNCTION [OPTIMIZER_INFO] [MC_INFO] [TIME=VALUE]
+ [INTERP_MODE=LINEAR|QUADRATIC|SAMPHOLD|HISTOGRAM|SPECTRAL]
```


## S, Y, Z Parameter Output File Specification

```
.FFILE S | Y | Z |G|H|T|A [SINGLELINE] FILENAME [HZ|KHZ|MHZ|GHZ] [RI|MA DB]
```


## Filter Data Driven Simulations

```
.FILTER AC|DC|TRAN|MODSST|SST|ALL [condition]
.FILTER EXTRACT [LABEL=label] [condition]
.FILTER DATA DATA_IN=input_data DATA_OUT=output_data [condition]
```


## Initial Transient Analysis Conditions

```
.FORCE [NODE] {node_name value}
+ [IND|OBJ] {object_name value}
```


## FFT Select Waveform

.FOUR LABEL = label_name waveform_name

## User Defined Function

.FUNC $P(a, b, \ldots)$ EXPR

## Global Node Allocation

.GLOBAL NN \{NN\}

## Initial DC Analysis Conditions

```
.GUESS V(NN)=VAL [SUBCKT=subckt_name] {V(NN)=VAL [SUBCKT=subckt_name]}
```


## Changing the Hierarchy Separator

.HIER . |/|<char>

## Initial Transient Analysis Conditions

.IC V(NN)=VAL [SUBCKT=subckt_name] \{V(NN)=VAL [SUBCKT=subckt_name]\}

## Ignore DSPF on Specified Node

 .IGNORE_DSPF_ON_NODE \{NODE\}Include a File in an Input Netlist .INC[LUDE] FNAME

## Initial Digital Circuit Conditions

```
.INIT NODE [DC=VAL] TI TS VALI {TI TS VALI}
```


## Current Probe

```
.IPROBE LABEL=vname [DIRECTION=POS|NEG ] pinref1 {pinrefn}
```


## Insert Circuit Information from a Library File

```
.LIB [KEY=KNAME] FNAME [LIBTYPE]
```

.LIB LIBTYPE

## Use Previously Simulated Results

.LOAD [FILE=]filename

## Insert a Feedback Loop

.LOOP INPUT OUTPUT [R|C|I|V VALUE] [DISCONNECT=DEV_NAME] [KEEPINPUT]

## Share Distributions

.LOTGROUP group_name[/distrib_type]=val[\%]

## Loop Stability Analysis

.LSTB SOURCE_NAME

## Model and Subcircuit Name Mapping

.MALIAS alias_model_name actual_model_name

## Map Eldo Node to DSPF Node

.MAP_DSPF_NODE_NAME LOGICAL=ELDONAME DSPF=NEWNAME

## Monte Carlo Analysis

```
.MC RUNNO [OUTER] [OV] [SEED=integer_value] [NONOM] [ALL]
+ [VARY=LOT|DEV] [IRUN=val] [NBBINS=val] [ORDMCS] [MCLIMIT]
+ [PRINT_EXTRACT=NOMINAL|ALL|run_number] [SIGBIN=val]
+ [MAXABSBIN=val] [MAXRELBIN=val]
```


## LOT \& DEV Variation Specification on Model Parameters (Monte Carlo)

```
.MCMOD MNAME [(list_of_instances)] PAR LOT|DEV=VAL {PAR LOT|DEV=VAL}
.MCMOD MNAME PAR LOTGROUP=my_lot_group
```


## Measure Waveform Characteristics

```
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name
+ TRIG trig_spec TARG targ_spec
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name WHEN when_spec AT val
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name FIND wave WHEN when_spec
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name FIND wave AT val
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name FIND W('wave')
+ WHEN when_spec [FROM=val] [TO=val]
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name DERIVATIVE wave
+ WHEN when_spec
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name DERIVATIVE wave AT val
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name meas_k wave
+ [FROM=val] [TO=val]
.MEAS [ANALYSIS_INFO] [VECT] [CATVECT] label_name PARAM='expression'
```


## Aspire/SimPilot Command

```
.MODDUP device_name [... device_name]
.MODDUP element_name
```


## Device Model Description

.MODEL MNAME TYPE NONOISE [PAR=VAL] .MODEL LIB FILENAME MODNAME [LIBTYPE]

Monitor Simulation Steps

```
.MONITOR ANALYSIS [=] [modulo]
```


## Multi-Processor Simulation

```
.MPRUN [ALL|HOST={host[(nbjobs)]}|FILE=filename}] [NBLICENSES=val]
+ [MAX_NBJOBS=val] [CLEAN=YES|NO] [QUEUE=YES|NO] [SETENV=YES|NO]
+ [VIEW_COMMAND=YES|NO] [CHECK_DELAY=val] [INIT_FILE=filename]
+ [DEFAULT_INIT=YES|NO] [NETWORK_DIR=directory]
+ [CD_WORKDIR=YES|NO] [LOGFILE=YES|NO]
+ [SHELL_SYNTAX=(source_cmd, setenv_cmd, setenv_sep, init_anacad_ext)]
+ [USE_LOCAL_HOST=YES|NO] [FLAT=YES|NO]
+ [FILE_PREFIX=(name1, name2,...,nameX)]
+ [USE_SSH=YES|NO] [SSH_OPTIONS="{<options>}"]
+ [CHECK_ALL_HOSTS=YES|NO]
```

```
+ [SYNCHRO_NOMINAL_MC=YES|NO]
.MPRUN DISPATCHER= [LSF |
+ (dispatcher_name, install_check_cmd, submission_cmd]
+ [REMOVE_QUOTE=YES|NO] [DISPATCHER_OPTIONS=options]
+ [NBLICENSES=val] [MAX_NBJOBS=val] [CLEAN=YES|NO]
+ [QUEUE] [SETENV] [VIEW_COMMAND] [CHECK_DELAY=val]
+ [INIT_FILE=filename [DEFAULT_INIT=YES|NO]]
+ [USE_LOCAL_HOST=YES|NO] [FLAT=YES|NO]
+ [FILE_PREFIX=(name1, name2,...,nameX)]
+ [LSF_JOB_PREFIX=lsf_prefix]
.MPRUN
+ DISPATCHER_TEMPLATE=command_line
+ [USE_LOCAL_HOST=YES|NO] [FLAT=YES|NO]
+ [FILE_PREFIX=(name1,name2,...,nameX)]
```


## Automatic Model Selection

```
.MSEL[LECT] dummy [MODELS] mod1 [mod2 [mod3 [...]]]
```


## Network Analysis

- 2-port network
.NET output input RIN=val ROUT=val
- 1-port network
.NET input RIN=val


## Control Page Layout

.NEWPAGE

## Suppress Comment Lines from Output File

. NOCOM

## DC Analysis Conditions

. NODESET $\mathbf{V}(N N)=V A L \quad\left[S U B C K T=s u b c k t \_\right.$name] $\left\{\mathbf{V}(N N)=V A L \quad\left[S U B C K T=s u b c k t \_n a m e\right]\right\}$

## Noise Analysis

.NOISE OUTV INSRC NUMS

## Transient Noise Analysis

```
.NOISETRAN FMIN=VAL FMAX=VAL NBRUN=VAL [NBF=VAL] [AMP=VAL]
+ [SEED=VAL] [NOMOD=VAL] [NONOM] [TSTART=VAL] [TSTOP=VAL]
+ [MRUN] [ALL] [NBBINS=VAL] [FMIN_FLICKER=VAL]
```


## Suppress Netlist from an Output File

.NOTRC

## Partition Netlist into Newton Blocks

```
.NWBLOCK [RELTOL=value] [VNTOL=value] list_of_nodes
```


## Optimization Objectives

```
. OBJECTIVE
+ EXTRACT_INFO [LABEL=NAME]
+ {$MACRO|FUNCTION}
+ OBJECTIVE_INFO
+ [SCALING_INFO]
+ [PRINT_INFO]
```


## DC Operating Point Calculation

```
.OP [[KEYWORD] T1 {[KEYWORD] TN}]
.OP TIME=VAL|END [STEP=VAL] [TEMP=VAL]
.OP DC=VAL [DC2=VAL] [STEP=VAL] [TEMP=VAL]
```


## DC Operating Point Display

```
.OP_DISPLAY
+ [MODEL=model_name]
+ [VTMOD=0|1|2]
+ [VTVDS=vds]
+ [VTCIDS=ids_norm]
+ [VTVGSMIN=vgsmin]
+ [VTVGSMAX=vgsmax]
```


## FFT Post-processor Options

```
.OPTFOUR [TSTART=VAL|EXPR] [TSTOP=VAL EXPR] [NBPT=VAL] [FS=VAL]
+ [NORMALIZED=0|1] [INTERPOLATE=0|112|3] [NOROUNDING[=1]] [RAPWIN=VAL]
+ [WINDOW=name] [ALPHA=VAL] [BETA=VAL] [PADDING=1|2|3]
+ [FMIN=VAL] [FMAX=VAL] [FNORMAL=freq] [DISPLAY_INPUT=0|1]
```


## Optimization

```
.OPTIMIZE [qualifier=value {, qualifier=value }]
+ [PARAM=list_of_parameters | *] [RESULTS=list_of_targets | *]
```


## Simulator Configuration

```
.OPT[ION] OPTION[=VAL] {OPTION[=VAL]}
```


## AC Noise Analysis

```
.OPTNOISE [ALL ON|OFF] [<CLASS> ON|OFF]
+ [R ON|OFF|<max>] [OUTSOURCE ON|OFF] [NSWEIGHT <FILENAME>]
+ [SORT D|V TD|TV [SN <n>|SV <value>]] [NBW <FMIN> <FMAX>]
```


## Accuracy by Time Window

```
.OPTPWL PARAM=((TIME1,VALUE1) (TIME2,VALUE2)...)
+ PARAM=((TIME1,VALUE1)...))
```


## Accuracy by Time Window

```
.OPTWIND PARAM=(TIME1,TIME2,VALUE1)... (TIME1N,TIME2N,VALUEN)
```


## Global Declarations

```
.PARAM PAR=VAL {PAR=VAL}
.PARAM PAR=EXPR {PAR=EXPR}
.PARAM PAR="NAME"
.PARAM PAR (a,b)=EXPR
.PARAM PAR=VAL|PAR=EXPR
+ LOT|DEV[/GAUSS|/UNIFORM|/USERDIST]=VAL|(dtype,-3sig,+3sig
+ [,bi,-dz,+dz [,off,sv] [,scale])
.PARAM PAR=VAL LOTGROUP=my_lot_group
.PARAM PAR=MC_DISTRIBUTION
.PARAM PAR=VAL DEVX=VAL
```


## Statistical Parameter Declarations

```
.PARAMDEX FACTOR_NAME [NOISE/] SIG=NSIGMA
.PARAMDEX FACTOR_NAME [NOISE/] RNG=NRANGE
.PARAMDEX FACTOR_NAME [NOISE/] ABS=DELTA
.PARAMDEX FACTOR_NAME [NOISE/] REL=DELTA%
.PARAMDEX FACTOR_NAME [CTRL/] ABS=DELTA [,NOM=RVALUE]
.PARAMDEX FACTOR_NAME [CTRL/] REL=DELTA% [,NOM=RVALUE]
```


## Optimization Parameter Declarations

```
.PARAMOPT VARIABLE_NAME=(
+ [INIT_VALUE,]
+ {LOWER_BOUND LOWER_PERCENT% },
+ {UPPER_BOUND | UPPER_PERCENT% }
+ [, INCREMENT])
```


## Circuit Partitioning

```
.PART ADIT|ELDO|MODSST
+ INST=(<instance_list>) SUBCKT=(<subcircuit_list>)
```


## Plotting of Simulation Results

```
.PLOT [ANALYSIS] OVN [(LOW, HIGH)] [(VERSUS)]
+ {OVN [(LOW, HIGH)]} [UNIT=NAME] [(SCATTERED)] [STEP=value]
.PLOT AC|FSST S(i, j) [(SMITH[,zref])] [(POLAR)]
.PLOT FOUR FOURxx(label_name) [(SPECTRAL)] [(CONTINUOUS)]
.PLOT DSP DSPxx(label_name)
.PLOT EXTRACT [MEAS | SWEEP]
.PLOT [CONTOUR] MEAS (meas_name_x) MEAS (meas_name_y) [(SCATTERED)]
+ [(SMITH[,zref])] [(POLAR)]
.PLOT [ANALYSIS] TWO_PORT_PARAM [(SMITH[,zref])] [(POLAR)]
```


## Plotting of Bus Signals

```
.PLOTBUS BNAME [VTH[1]=VAL1 [VTH2=VAL2]]
+ [BASE=OCT|DEC|BIN|HEX] [RADIX=UNSIGNED| 2COMP] [ (ANALOG)]
.PLOTBUS BNAME[MSB:LSB]|BNAME<MSB:LSB>|BNAMEMSB:LSB
+ [BASE=OCT|DEC|BIN|HEX] [RADIX=UNSIGNED|2COMP] [(ANALOG)]
```


## Printing of Results

```
.PRINT [ANALYSIS] [alias_name=]OVN
```


## Printing of Bus Signals

```
.PRINTBUS BNAME [VTH[1]=VAL1 [VTH2=VAL2]]
+ [BASE=OCT|DEC|BIN|HEX] [RADIX=UNSIGNED|2COMP]
.PRINTBUS BNAME[MSB:LSB]|BNAME<MSB:LSB>|BNAMEMSB:LSB
+ [BASE=OCT|DEC|BIN|HEX] [RADIX=UNSIGNED|2COMP]
```


## Print Tabular Output File

```
.PRINTFILE [ANALYSIS] OVN FILE=filename [STEP=value]
+ [START=value] [STOP=value] [FORMAT=DATA]
```


## Output Shortform

```
.PROBE [ANALYSIS] [ALL|I|IX|ISUB|PORT|PRINT|SG|SPARAM|S|Q|V|VN|VTOP|
+ VX|VXN|W|WTOP] [MASK=mask_name] [EXCEPT=pattern] [PRINT] [STEP=val]
+ [DELTA=val]
.PROBE [ANALYSIS] [MASK=mask_name] [EXCEPT=pattern] [alias_name=] OVN
+ [PRINT] [STEP=val] [DELTA=val]
```


## Printing of Bus Signals

```
.PROBEBUS BNAME [VTH[1]=VAL [VTH2=VAL]]
.PROBEBUS BNAME[MSB:LSB]|BNAME<MSB:LSB>|BNAMEMSB:LSB
```


## Netlist Protection

.PROTECT

## Pole-Zero Analysis

.PZ OV

## Automatic Ramping

```
.RAMP DC VAL [SIMPLIFY]
.RAMP TRAN T1 T2 [SIMPLIFY]
```


## Restart Simulation

```
.RESTART FNAME [FILE=WNAME]
.RESTART ["fileBasename"] [NEWEST|LONGEST|TIME=VALUE] [FILE=WNAME]
```


## Save Simulation Run

```
.SAVE [[FILE=]FNAME] DC|END|TIME=VAL1 [REPEAT] [ALT|SEQ]
+ [TEMP=VAL2] [STEP=VAL3] [TYPE=NODESET|IC] [LEVEL=ALL|TOP] [CARLO=index]
```


## Automatic Scaling of Active Devices

```
.SC[ALE] ELTYPE KEYWORD VALUE [KEYWORD VALUE ...]
+ [ELEMENTS ALL | EXCEPT] [ELNAME1 ELNAME2 ...] [(ELNAME1 ELNAME2)]]
.SC[ALE] ELTYPE KEYWORD VALUE [KEYWORD VALUE ....]
+ MODELS MODNAME1 [MODNAME2 ...]
.SC[ALE] MODTYPE KEYWORD VALUE [KEYWORD VALUE ....]
+ [MODELS ALL |EXCEPT] [MODNAME1 MODNAME2] [(MODNAME1 MODNAME2...)]]
.SC[ALE] P FACTOR=VALUE [SUBCKT=SUBNAME]
+ [PARAMS ALL | EXCEPT] [PARAM1 PARAM2 ...] [(PARAM11 PARAM22)]]
```


## Select DSPF on Specified Node

```
.SELECT_DSPF_ON_NODE {NODE}
```

DC Sensitivity Analysis

.SENS OVN \{OVN\}

## AC Sensitivity Analysis

.SENSAC OVN \{OVN\} FREQ=val1[\{,val2\}] [SORT_REL] [SORT_ABS] [SORT_MAX]

## Sensitivity Analysis

```
.SENSPARAM sub[ckt]=subckt_name param=parameter_list
```

+ [var[iation]=value] [inst[ance]=instance_list]
+ [sort=inc[reasing] | dec[reasing] | alpha[betical]]
+ [sort_nbmax=value] [sort_abs=value | sort_rel=value]


## Create Bus

. SETBUS BNAME PN \{PN\}

## Set Reliability Model Key (Password)

```
.SETKEY [MODEL=model_name] KEY=key_value
```


## Set Safe Operating Area

```
.SETSOA [LABEL="<STRING>"] [ANALYSIS]
+ E {EXPRESSION=(MIN,MAX[,XAXIS])}
.SETSOA [LABEL="<STRING>"] [ANALYSIS]
+ E IF (EXPR) THEN({PARAM=(MIN,MAX[,XAXIS])})
+ ELSE({PARAM=(MIN,MAX[,XAXIS])}) ENDIF
.SETSOA [LABEL="<STRING>"] [ANALYSIS]
+ D DNAME [SUBCKT=subckt_list|INST=inst_list] {PARAM=(MIN,MAX[,XAXIS])}
.SETSOA [LABEL="<STRING>"] [ANALYSIS]
+ D DNAME [SUBCKT=subckt_list|INST=inst_list]
```

```
+ IF(EXPR) THEN({PARAM=(MIN, MAX[, XAXIS])})
+ ELSE({PARAM=(MIN, MAX[, XAXIS])}) ENDIF
.SETSOA [LABEL="<STRING>"] [ANALYSIS]
+ M MNAME [SUBCKT=subckt_list|INST=inst_list] {PARAM=(MIN,MAX[,XAXIS])}
.SETSOA [LABEL="<STRING>"] [ANALYSIS]
+ M MNAME [SUBCKT=subckt_list|INST=inst_list]
+ IF(EXPR) THEN({PARAM=(MIN, MAX[, XAXIS])})
+ ELSE({PARAM=(MIN, MAX[, XAXIS])}) ENDIF
```


## Set Bus Signal

```
.SIGBUS BNAME|BNAMEMSB:LSB|BNAME [MSB:LSB]|BNAME<MSB:LSB>
+ [VHI=VAL1] [VLO=VAL2] [TFALL=VAL3] [TRISE=VAL4]
+ [BASE=OCT|DEC|BIN|HEX] [SIGNED=NONE| 1COMP | 2COMP]
+ TN VAL {TN VAL} [P]
.SIGBUS BNAME|BNAMEMSB:LSB|BNAME [MSB:LSB]|BNAME<MSB:LSB>
+ [VHI=VAL] [VLO=VAL] [TFALL=VAL] [TRISE=VAL] [THOLD=VAL] [TDELAY=VAL]
+ [BASE=OCT|DEC|BIN|HEX] [SIGNED=NONE| 1COMP | 2COMP]
+ PATTERN $(PAT) {$(PAT)} VAL {VAL} [Z]
.SIGBUS BNAME|BNAMEMSB:LSB|BNAME[MSB:LSB]|BNAME<MSB:LSB>
+ [VHI=VAL] [VLO=VAL] [TFALL=VAL] [TRISE=VAL] [THOLD=VAL] [TDELAY=VAL]
+ [BASE=OCT |DEC|BIN|HEX] [SIGNED=NONE| 1COMP | 2COMP]
+ FILE=FILE
```


## Sinusoidal Voltage Source

```
.SINUS NODE VO VA FR [TD [THETA]]
```


## Spot Noise Figure

```
.SNF INPUT=(LIST_OF_DEVICES) OUTPUT=(LIST_OF_DEVICES)
+ [INPUT_TEMP=VAL] [NOISETEMP=VAL]
```


## Sizing Facility

```
.SOLVE PARAM param_name MIN MAX expr=expr [TOL=VAL]
+ [RELTOL=VAL] [GRID=VAL]
.SOLVE obj_name [W|L] MIN MAX expr=expr [TOL=VAL]
+ [RELTOL=VAL] [GRID=VAL]
.SOLVE CNAME [W|L] MIN MAX OPSIZE [TOL=VAL]
```


## Simulation Start Time

```
.START_TIME time_value
```


## Parameter Sweep

```
.STEP TEMP|DIPOLE INCR_SPEC
.STEP MOS W|L INCR_SPEC
.STEP MNAME PARAM_NAME INCR_SPEC
.STEP PARAM PARAM_NAME INCR_SPEC, {[VALSTART] VALSTOP VALUE}
.STEP ITEM INCR_SPEC {ITEM2 BOUND}
.STEP (ITEM1,ITEM2,...,ITEMn)
+ LIST | = (VALi1, VALi2... VALin)... (VALj1, VALj2... VALjn)
.STEP (ITEM1,ITEM2... ITEMn) LIST FILE=FILE
```


## Subcircuit Definition

```
.SUBCKT NAME NN{NN} [(SWITCH|ANALOG|OSR|DIGITAL)]
+ [(NONOISE)] [(INLINE)] [PARAM: PAR=VAL {PAR=VAL}] [STATISTICAL=0| 1]
<CIRCUIT_COMPONENTS>
.ENDS [NAME]
.SUBCKT LIB FNAME SNAME [LIBTYPE]
```


## Subcircuit Duplicate Parameters

```
.SUBDUP SUBCKT_INST_NAME
```


## Value Tables

.TABLE NAME (X1 Y1) \{(XN YN) \}

## Set Circuit Temperature

```
.TEMP TS {TS}
```


## Transfer Function

```
.TF OV IN
```


## Set Title of Binary Output File

```
.TITLE name
```


## Select the TOP Cell Subcircuit

```
.TOPCELL [=] <SUBCKT_NAME>
```


## Transient Analysis

```
.TRAN TPRINT TSTOP [TSTART [HMAX]] [SWEEP DATA=dataname] [UIC] [MONTE=val]
.TRAN TPRINT TSTOP [TSTART [HMAX]] [SWEEP parameter_name
+ TYPE nb start stop] [UIC] [MONTE=val]
.TRAN TPRINT TSTOP [TSTART [HMAX]] [SWEEP parameter_name start stop incr]
+ [UIC] [MONTE=val]
.TRAN INCRn Tn [{INCRn Tn}] [TSTART=val] [SWEEP DATA=dataname]
+ [UIC] [MONTE=val]
.TRAN INCRn Tn [{INCRn Tn}] [TSTART=val] [SWEEP parameter_name
+ TYPE nb start stop] [UIC] [MONTE=val]
.TRAN INCRn Tn [{INCRn Tn}] [TSTART=val] [SWEEP parameter_name
+ start stop incr] [UIC] [MONTE=val]
.TRAN DATA=dataname [SWEEP DATA=dataname] [UIC] [MONTE=val]
.TRAN DATA=dataname [SWEEP parameter_name TYPE nb start stop]
+ [UIC] [MONTE=val]
.TRAN DATA=dataname [SWEEP parameter_name start stop incr]
+ [UIC] [MONTE=val]
```


## Save Simulation Run at Multiple Time Points

.TSAVE [REPLACE|NOREPLACE] TIME=VALUE [FILE="FILEBASENAME"]

## Test Vector Files

.TVINCLUDE [FILE=]FILENAME [COMP=ON|OFF] [ERRNODE[=YES|NO]]

## Netlist Protection

.UNPROTECT

## Use Previously Simulated Results

.USE FILE_NAME [NODESET|IC|GUESS|OVERWRITE_INPUT]

## Use Reliability Model Key (Password)

```
.USEKEY [MODEL=model_name] KEY=key_value
```

Use Tcl File

```
.USE_TCL FILENAME [MODE=PPL|EZWAVE]
```


## Test Vector Files

.VEC 'file_name'

## Worst Case Analysis

.WCASE DC $\mid$ AC $\mid$ TRAN [OUTPUT=MIN $\mid$ MAX $\mid$ BOTH] [VARY=LOT $\mid$ DEV $\mid$ BOTH]

+ [TOL=VAL] [ALL] [SORT_REL=VAL] [SORT_ABS=VAL] [SORT_NBMAX=VAL]


## Set Printer Paper Width <br> .WIDTH OUT=80|132

## Chapter 4 <br> Device Models

## Summary

The following table summarizes the Device Models available.
Table 4-1. Eldo Device Models

| Resistor | Capacitor | Inductor | Coupled Inductor |
| :---: | :---: | :---: | :---: |
| RC Wire | Diffusion Resistor | Semiconductor Resistor |  |
| Transmission Line | Lossy Transmission Line | Lossy Transmission Line: W Model | Lossy Transmission Line: U Model |
| Microstrip Models |  |  |  |
| Junction Diodes | Berkeley Level 1 (Eldo Level 1) | Modified Berkeley Level 1 (Eldo Level 2) | Fowler-Nordheim Model (Eldo Level 3) |
|  | JUNCAP (Eldo Level 8) | Philips Diode Level 500 (Eldo Level 9) | Diode Level 21 |
|  | JUNCAP2 (Eldo Level 8, DIOLEV=11) |  |  |
| BJT—Bipolar Junction Transistors | Modified Gummel-Poon Model (Eldo Level 1) | Philips Mextram 503.2 Model (Eldo Level 4) | Improved Berkeley Model (Eldo Level 5) |
|  | VBIC v1.2 Model (Eldo Level 8) | VBIC v1.1.5 Model (Eldo Level 8) | HICUM Model (Eldo Level 9) |
|  | Philips Mextram 504 Model (Eldo Level 22) | Philips Modella Model (Eldo Level 23) | HICUM Level0 Model (Eldo Level 24) |
| JFET—Junction Field Effect Transistor |  |  |  |
| MESFET-Metal Semiconductor Field Effect Transistor |  |  |  |
| MOSFETs | Berkeley SPICE Models | MERCKEL MOSFET Models | Berkeley SPICE BSIM1 Model (Eldo Level 8) |
|  | Berkeley SPICE BSIM2 Model (Eldo Level 11) | Modified Berkeley Level 2 (Eldo Level 12) | Modified Berkeley Level 3 (Eldo Level 13) |
|  | Modified Lattin-JenkinsGrove Model (Eldo Level 16) | Enhanced Berkeley Level 2 Model (Eldo Level 17) | EKV MOS Model (Eldo Level 44 or EKV) |

Table 4-1. Eldo Device Models

| MOSFETs (cont.) | Berkeley SPICE BSIM3v2 <br> Model (Eldo Level 47) | Berkeley SPICE <br> BSIM3v3 Model (Eldo <br> Level 53) | Motorola SSIM Model <br> (Eldo Level 54 or SSIM) |
| :--- | :--- | :--- | :--- |
|  | Berkeley SPICE BSIMSOI3 <br> v1.3 Model (Eldo Level 55) | Berkeley SPICE <br> BSIMSOI3 v2.x and v3.x <br> Model (Eldo Level 56) | Philips MOS 9 Model <br> (Eldo Level 59 or <br> MOSP9) |
|  | Berkeley SPICE BSIM4 <br> Model (Eldo Level 60) | EKV3 MOS Model (Eldo <br> Level 61 or EKV3) | TFT Polysilicon Model <br> (Eldo Level 62) |
|  | Philips MOS Model 11 <br> Level 1101 (Eldo Level 63) | TFT Amorphous-Si <br> Model (Eldo Level 64) | Philips MOS Model 11 <br> Level 1100 (Eldo Level <br> 65) |
|  | HiSIM Model (Eldo Level <br> 66) | SP Model (Eldo Level <br> 67) | Philips MOS Model 11 <br> Level 1102 (Eldo Level <br> 69) |
|  | Philips PSP Model (Eldo <br> Level 70) | Philips MOS Model 20 <br> Level 2002 (Eldo Level <br> $71)$ | Berkeley SPICE <br> BSIMSOI4.0 Model <br> (Eldo Level 72) |
|  | HiSIM-LDMOS Model <br> (Eldo Level 73) | MOSVAR Model (Eldo <br> Level 74) | PSP103 Model (Eldo <br> Level 75) |
|  | HVMOS Model (Eldo Level <br> 101) |  |  |
| S-Domain Filter | Z-Domain Filter | Subcircuit Instance |  |

## Merging Devices in Parallel

By default, Eldo merges instances connected in parallel into a single instance. (Prior to the AMS2009.2 release this was only possible with . OPtion reduce.) The parallel instances must have the same set of parameters, and follow each other in the netlist. The multiple instances are reduced into a single instance by Eldo with the m parameter, for example:

```
x1 1 2 FOO A=1 B=1
x2 1 2 FOO A=1 B=1
x3 1 2 FOO A=1.0 B=1
```

Here, $x 3$ will remain as it is because the character string for A does not match, but X instances x 1 and x 2 will be replaced by:

X1 12 FOO $A=1 \quad B=1 \quad \mathbf{M}=2$
This behavior applies to:

- Resistors, see "Combining Identical Resistors" on page 126,
- Diodes, see "Combining Identical Diodes" on page 227,
- BJTs, see "Combining Identical BJTs" on page 234,
- MOSFETs,see "Combining Identical MOSFETs" on page 252
- Subcircuit instances, see "Combining Identical Subcircuits" on page 303

The merging is done in order to speed-up simulations. However, this may also result in unexpected warnings in the following situations:

- If a device name is specified in a .PRINT/.PLOT/.EXTRACT, and if this device is merged with another, Eldo will issue a warning that the device is not found. For example, with .PRINT dc ix(x2.1) Eldo will issue a warning that device x 2 is not found.
- Output may take into account the M factor. For example, .PRINT IX(X1.1) will return twice the value which would be obtained if devices had not been merged.
- Option MINRVAL has a different impact:

If option MINRAVL is specified, and if there are resistors inside some X instances which are merged, the working resistance of the device is $R / M$, ( $M$ being the number of items in parallel. R/M can become inferior to MINRVAL while R was superior to MINRVAL. This should have limited impact on the results.

To disable merging devices in parallel, specify option nосатмх or invoke Eldo with the -nocatmx flag.

## Notes

- Monte Carlo results may vary in case devices are merged, simply because the number of random parameters to be extracted per run will not be the same. Providing that the number of Monte Carlo runs is large enough, the Monte Carlo results should be the same.
- This feature is disabled when a .DSPF_INClude command is inside the netlist.
- Instances inside Verilog-A instances are never merged.


## Device Models

## Resistor

```
Rxx N1 N2 [MOD[EL]=MNAME] [VAL] [[TC1=]T1] [[TC2=]T2] [[TC3=]T3]
+ [AC=VAL|{EXPR}] [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [L=VAL] [W=VAL]
+ [STATISTICAL=0|1] [KEEPRMIN] [NONOISE] [NOISE=1] [KF=VAL] [AF=VAL]
+ [WEEXP=VAL] [LEEXP=VAL] [FEXP=VAL] [FMIN=VAL] [FMAX=VAL] [NBF=VAL]
Rxx N1 N2 [MOD[EL]=MNAME] [VALUE|R=]{EXPR} [ACDERFUNC=0|1]
+ [RESTORE_CAUSALITY=0|1] [[TC1=]T1] [[TC2=]T2] [[TC3=]T3] [AC=VAL]
+ [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [STATISTICAL=0|1] [KEEPRMIN] [NONOISE]
+ [NOISE=1] [KF=VAL] [AF=VAL] [WEEXP=VAL] [LEEXP=VAL] [FEXP=VAL]
+ [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [FIT=0|1] [CFMAX=VAL] [CDELF=VAL]
Rxx N1 N2 [[TC1=]T1] [[TC2=]T2] [[TC3=]T3] [AC=VAL] [T[EMP]=VAL]
+ [DTEMP=VAL] [M=VAL] [KF=VAL] [AF=VAL] [WEEXP=VAL] [LEEXP=VAL]
+ [FEXP=VAL] [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]
+ TABLE EXPR [KEEPRMIN] [NONOISE] [NOISE=1]
Rxx NP NN POLY VAL {COEF} [TC1=T1] [TC2=T2] [TC3=T3] [STATISTICAL=0|1]
```


## Parameters

- xx

Resistor name.

- N1, N2

Names of the resistor nodes.

- VAL

Value of resistor in $\Omega$ at nominal temperature. This value can be assigned directly or via the . PARAM command. Optional if a resistor model is used. For more information, see ".PARAM" on page 778.

## Note

If a parameter name is required to be specified as the 4th token of the syntax, enclose it in braces \{ \}, single quotes ' ', or use the syntax $r=$ param_name to distinguish it from the model name.

- MOD [EL] =MNAME

Model name.

- TC1, TC2, TC3

First, Second, and Third order temperature coefficients. Default values are zero. The temperature coefficients can be expressed simply as values, without the $\mathbf{T C 1}=$ for example. тс3 can be specified even if $\mathbf{T C 1 / T C 2}$ are not: they would default to zero.

- poly

Keyword to identify the resistor as non-linear polynomial.

## Note

Instead of using the poLy keyword, you can also specify parameters VC1=value and
$\mathrm{VC2}=$ value. $\mathrm{VC1}$ is equivalent to the first parameter of the polynomial array, VC2 is
equivalent to the second parameter of the polynomial array.

- Coef

Polynomial coefficients used to calculate the voltage dependency of the resistor. The value of the resistor is computed as:

$$
\text { Resistor Value }=V A L+R 1 \times V+R 2 \times V^{2}+\ldots+R n \times V^{n}
$$

where V is the voltage across the resistor.

- AC=VAL

Specifies the resistor value, in $\Omega$, which is used in AC analysis only.

- $\mathbf{A C}=\{\operatorname{EXPR}\}$

Enables the instantiation of a resistor with a functional expression to be simulated in AC analysis.

- VALUE $=\{\operatorname{EXPR}\} \mid \mathbf{R}=\{\operatorname{EXPR}\}$

Keyword indicating that the resistor has a functional description. This enables the instantiation of a frequency-dependent resistor to be simulated in all analysis modes (AC, Transient, SST and MODSST). The expression can make use of the freq keyword to specify frequency. A typical application is to model skin-effect, with $R$ varying according to SQRT (FREQ).

## Note

If VALUE=\{EXPR\} is frequency based then the allowed syntax is as follows:
RXX NP NN VALUE=\{EXPR\} [TC1=T1] [TC2=T2] [TC3=T3]
VALUE $=\{\operatorname{EXPR}\}$ and $\mathrm{AC}=\{\operatorname{EXPR}\}$ correspond to two different syntaxes, both accepted by Eldo, but they cannot be specified together.
VALUE $=\{E X P R\}$ can be used together with AC=VAL only when VALUE $=\{E X P R\}$ is not frequency based.
If the value of the resistor is defined by a value expression, the actual value will be recalculated at each timestep during transient analysis. However, if an AC analysis is performed, the value is calculated only once in the DC analysis, and then considered to be static.

- ACDERFUNC=0|1

Derivative of function selector for AC analysis only. For voltage or current dependent resistors, the derivatives of the value with respect to the voltage are dumped in the matrix by default. Setting acderfunc to 0 forces Eldo to ignore these derivatives when generating the matrix. The specification on the device overrides any global setting by options acderfunc (set by default) or noacderfunc.

- RESTORE_CAUSALITY=0|1

Having a purely real impedance that varies with the square root of frequency is not physically realizable. It would be non-causal. Thus when modeling a physical resistance, specifying a variation as the square root of frequency can be interpreted by Eldo as either:

- specifying the module of the impedance (default, or ReSTORE_CAUSALITY=0), or
- specifying the real part of the impedance, and Eldo computes the imaginary part
(RESTORE_CAUSALITY=1)
For transient simulation, Eldo fits R with a rational function $\mathrm{H}(\mathrm{s})$, where $s=j \times w$. In the first case, $H(s)$ is found so that its module best fits $R(f)$. In the second case, $H(s)$ is found so that its real part best fits $\mathrm{R}(\mathrm{f})$.
There is however a better way to approach frequency dependent resistor and inductance modeling, which is to specify both the real part $(\mathrm{R}(\mathrm{f})$ ) and imaginary part ( $\mathrm{jw} \times \mathrm{L}(\mathrm{f})$ ) of impedance, with a relationship that maintains causality: this is possible using the syntax:

```
Lxx N1 N2 value={expr} R value={expr}
```

- $\mathbf{T}[$ EMP $]=$ VAL

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- DTEMP=VAL

Temperature difference between the device and the rest of the circuit, in degrees Celsius. Default value is 0.0.

## Note

TEMP and DTEMP are mutually exclusive. If both are specified, the last one is used.

- $\mathbf{M}=$ VAL

Device multiplier, simulating the effect of multiple devices in parallel: effective resistance value is divided by m. Default is 1 .

The device is first evaluated without the $m$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values w and $\mathbf{L}$ are not affected. Models are chosen depending on input w and $\mathbf{L}$, if required. Options minc, MAXL, MINW, MAXw, and so on, do not apply either, since they check the input values of w and L .

Note
Using an M factor value less than 1 could lead to simulating devices that cannot be physically realized.

- STATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option Statistical. Default is 1 .

- KEEPRMIN

Any effect of rmminrval and minrval options will be ignored for the device. This is a way to force Eldo to keep the device under all circumstances unless the device is equal to zero.

- NONOISE

Specifies that no noise model will be used for this device when performing noise analysis. Therefore, the device presents no noise contribution to the noise analysis.

- NOISE=1

Specifies that a noise model will be used for this device when performing noise analysis.
Therefore, the device presents noise contribution to the noise analysis. This has precedence over any nonoise specification on a .MODEL card.

- table

Keyword indicating that the resistor accepts a table description.

- $\mathrm{kF}=\mathrm{VAL}$

Flicker noise coefficient. Default is 0 .

- $\mathbf{A F}=\mathrm{VAL}$

Flicker noise exponent. Default is 1.0.

- WEEXP=VAL

Flicker noise exponent. Default is 0.0.

- LEEXP=VAL

Flicker noise exponent. Default is 0.0.

- FEXP=VAL

Flicker noise exponent. Default is 1.0. Flicker noise equation is:

$$
\text { Sid }=K F \cdot \frac{I^{A F}}{W_{e f f}^{W E E X P} \cdot L_{e f f}^{L E E X P} \cdot \text { freq }^{F E X P}}
$$

- $\quad$ FMIN=VAL

Lower limit of the noise frequency band.

- $\quad$ FMAX=VAL

Upper limit of the noise frequency band.
Note
FMIN and FMAX define the frequency band of the noise sources. This frequency range
may sometimes not correspond to the noise frequency band at the output of the circuit.
For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency
band in the case of filters or oscillators and mixers that exhibit frequency conversion.
FMIN is also used to specify the algorithm used to generate the noise source generated by
the resistor. When FMIN>0 the resistor noise source is generated with sinusoids; when
FMIN $=0$ it is generated with a continuous spectrum between $\operatorname{FMIN}$ and FMAX.

- $\quad \mathrm{NBF}=\mathrm{VAL}$

Specifies the number of sinusoidal sources with appropriate amplitude and frequency and with randomly distributed phase from which the noise source is composed. Default value is 50. This parameter has no effect when FMIN is set to 0 .

- $\boldsymbol{F I T}=0 \mid 1$

Specifies the method used to perform transient analysis. $\operatorname{FIT}=1$ indicates the fitting method is used, FIT=0 indicates the convolution method is used. Default value is 1 .

- CFMAX=VAL

Specifies the maximum frequency value used in the functional description of the resistor. It is used in transient analysis to perform impulse response using a convolution method.
Default is $1.0 \times 10^{9} \mathrm{~Hz}$. Can only be used when $\mathrm{FIT}=0$.

- CDelf=VAL

Specifies the frequency interval to compute the functional description of the resistor. It must have the form $2^{\mathrm{n}}$ for the convolution computation (automatic check and correction are done if not). Default is $1.0 \times 10^{9} / 1024=9.765625 \times 10^{5} \mathrm{~Hz}$. Can only be used when FIT $=0$.

## Note

The parameters fit, cfmax, cdelf should only be used when the resistor is frequency dependent, else they will be ignored.

The user can specify the minimum value that resistors in the netlist can take using the option RSMALL. For more information please refer to "RSMALL=VAL" on page 990.

## Combining Identical Resistors

Multiple identical resistors connected in parallel are reduced into a single instance using the m parameter, for example:

```
r1 1 2 res1
r2 1 2 res1
r3 1 3 res1
```

Here, r 3 will remain as it is because it is connected to different nodes, but resistor instances r1 and r 2 will be replaced by:

```
r1 1 2 res1 M = 2
```

Note
It will only work when no parameters are given on the instance.

For more information see "Merging Devices in Parallel" on page 120.

## Noise in Resistors



The thermal noise of a resistor is as follows:

$$
S I=\frac{4 \times k \times T}{R}
$$

## Examples

r1 n3 n4 3.3k

Specifies a $3.3 \mathrm{k} \Omega$ resistor placed between nodes n 3 and n 4 .

```
r2 n1 n2 rval
.param rval=2k
```

Specifies a resistor named r 2 of value rval between nodes n 1 and n 2 . The resistor value is declared globally in the .PARAM command.

```
r3 1 2 value={2k*v(3,4)*i(v5)}
```

Specifies a resistor r 3 between nodes 1 and 2 whose value is described by the expression in curly brackets.
rg4 45 table $(v(p 3 n))=(0,1 e 11)(1 v, 1 e 3)$
The value of resistor rg 4 is $1 \times 10^{11} \Omega$ when $\mathrm{v}(\mathrm{p} 3 \mathrm{n})=0 \mathrm{~V}, 1 \mathrm{k} \Omega$ when $\mathrm{v}(\mathrm{p} 3 \mathrm{n})=1 \mathrm{~V}$. The other values are interpolated.

```
r5 1 2 value={50*sqrt(1+(FREQ/10e6))}
```

Specifies a frequency-dependent resistor r 5 between nodes 1 and 2 whose value is described by the expression in curly brackets.

```
r1 1 2 ac=3 value={2k*v(3,4)*i(v5)}
```

Specifies a resistor $r 1$ between nodes 1 and 2 whose value is described by the expression in curly brackets. This value is superseded when an AC analysis is performed, where the ac value is used instead, in this case $3 \Omega$.

```
r2 3 4 value={50*sqrt(1+(FREQ/10e6))} tc1=0.001
+ tc2=0.004 tc3=0.003
```

Specifies a frequency dependent resistor $r 2$ between nodes 3 and 4 , whose value is described by the expression in curly brackets, that also has first, second and third order temperature coefficients.

```
r1 1 2 value = {1k + 2k*v(1)} ACDERFUNC = 1
```

Specifies a voltage dependent resistor. The derivatives of the value with respect to the voltage are dumped in the matrix because acderfunc (derivative of function selector) is set to 1 , therefore the term 2 k will be in the matrix. By default (without ACDERFUNC) it will not be in the matrix.

## Resistor Model Syntax

. MODEL MNAME R[ES] [\{PAR=VAL\}]
Note
Specifying sCALM=val in the .MODEL statement in a resistor model overrides the global scaling specified by the .OPTION SCALM=val statement.

## Level 1

Table 4-2. Resistor Model—Level 1 Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | R or <br> SCALE[R] | Resistance multiplier | 1 |  |
| 2 | RDEF | Value of resistor. This value has priority over values <br> computed from L and W | $1 \times 10^{3}$ | $\Omega$ |
| 3 | POLY ${ }^{1}$ | Keyword to identify the resistor as non-linear <br> polynomial | Used to change the formula used for computing the R <br> value | 2 |
| 4 | POLYV | Used to change the formula used for computing the R <br> value | 0 |  |
| 5 | REVSP |  |  |  |

Table 4-2. Resistor Model—Level 1 Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 6 | TC1 | First order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-1}$ |
| 7 | TC 2 | Second order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-2}$ |
| 8 | TC 3 | Third order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-3}$ |
| 9 | LOT | Correlated device tolerance (Monte Carlo analysis) |  |  |
| 10 | DEV | Uncorrelated device tolerance (Monte Carlo analysis) |  |  |
| 11 | NOISE | Noise contribution of resistor ${ }^{2}$ | 1.0 |  |
| 12 | WEEXP | Flicker noise exponents | 0.0 |  |
| 13 | LEEXP |  | 0.0 |  |
| 14 | FEXP |  | 1.0 |  |
| 15 | TNOM | Nominal temperature | 27 | ${ }^{\circ} \mathrm{C}$ |

1. Instead of using the POLY keyword, you can also specify parameters VC1=value and VC2=value. VC1 is equivalent to the first parameter of the polynomial array, VC2 is equivalent to the second parameter of the polynomial array.
2. Noise contribution of the resistor will be expressed as $4 \times \boldsymbol{K} \boldsymbol{B} \times \mathbf{T} \times \mathbf{N O I S E} / \mathbf{R}$. Where $\boldsymbol{K} \boldsymbol{B}$ is the Boltzmann coefficient.

The below equation defines resistor value as a function of temperature, where T is the operating temperature specified either by the .TEMP command, or the $\boldsymbol{T}$ parameter. Tnom is the nominal temperature for which the resistor has resistance VAL. Default value of Tnom is $27^{\circ} \mathrm{C}$ and is adjustable using . OPTION TNOM.

$$
R V A L(T)=V A L\left(T_{n o m}\right)\left(1+\mathrm{TC} 1\left(T-T_{n o m}\right)+\mathrm{TC} 2\left(T-T_{\text {nom }}\right)^{2}+\mathrm{TC} 3\left(T-T_{\text {nom }}\right)^{3}\right)
$$

The Resistor model has additional levels for the .model card.

TC1, TC2, TC3 and R are used by model levels 1, 2, 3 and 4.

## POLY usage

The poly keyword identifies the model as a non-linear polynomial. It applies to the resistance/capacitance/inductor model syntax and is accepted on the model card in which the coefficients are used to generate $\mathrm{R}, \mathrm{C}$ or L values which are dependent on bias. Syntax:

```
.MODEL <model_name> [R|C|IND] POLY <list_of_parameter_values>
```

This polynomial list can be given in addition to existing model parameters, for example:

```
.MODEL <model_name> R TC1=0.1 POLY <list_of_parameter_values>
+TC2=0.2
```

The bias independent value of the resistor will be computed as if there were no polynomial parameters. Then, the active value of the resistor will be equal to the product of the "biasindependent value" multiplied by the polynomial expression.

Notes:

- poly can be specified in a capacitance instance the same way it is used for resistance.
- Instead of using the poly keyword, you can also specify parameters vc1=value and VC2=value. VC1 is equivalent to the first parameter of the polynomial array, vc2 is equivalent to the second parameter of the polynomial array.


## REVSP and POLYV usage

- Parameter polyv can also be specified on the .model card. polyv can take two values: equal to 2 or not equal to 2 . It will be used to change the formula which is used for computing the R/L/C value. Assuming the model:

```
.MODEL FOO C POLY P1 P2 P3... Pn
C pin1 pin2 Foo <cinst>
```

If $V=V(p i n 1)-V(\operatorname{pin} 2):$
then if polyv is 2 : the value of C will be computed as:

$$
\mathrm{C}=\langle\text { cinst }\rangle \times\left(\mathrm{P} 1+\mathrm{P} 2 \times \mathrm{V}+\mathrm{P} 3 \times \mathrm{V}^{2}+\ldots\right)
$$

if polyv is not 2 : the value of C will be computed as:

$$
\mathrm{C}=\left\langle\text { cinst }>\times\left(1+\mathrm{P} 1 \times \mathrm{V}+\mathrm{P} 2 \times \mathrm{V}^{2}+\ldots\right)\right.
$$

P1and P2 represent the polynomial coefficients. The default value for polyv is 2 .

- Parameter flag revse can also take two values: equal to 1 or not equal to 1. polyv and REVSP parameters are flags to modify computations. They do not interact directly within the computation. If parameter revsp is set to 1 on the .model card, and if polyv is not 2 , then the formula for computing the current generated by the resistor is:

$$
I=\frac{V}{\text { rinst }} \times\left(1+\frac{P 1 \times V}{2}+\frac{P 2 \times V^{2}}{3}+\ldots\right)
$$

which leads to a resistor of value:

$$
R(V)=\frac{1}{\delta I / \delta V}=\frac{\text { rinst }}{\left(1+P 1 \times V+P 2 \times V^{2}+\ldots\right)}
$$

P1and P2 represent the polynomial coefficients. The default value for revsp is 0 .

## Example

```
.model rmodel res tc1=0.001 tc2=0.005 tc3=0.008
...
r2 n1 n19 rmodel 2.5k
```

Specifies a $2.5 \mathrm{k} \Omega$ resistor placed between nodes n 1 and n 19 . The first order temperature coefficient is 0.001 , the second order temperature coefficient is 0.005 , and the third order temperature coefficient is 0.008 , all being defined using the . MODEL command.

## Level 2

This is a private ST model. For a description of equations please contact STMicroelectronics. This is the default model when the -stver flag is specified (or option stver). Parameters:

Table 4-3. Resistor Model—Level 2 Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | RHO | Sheet resistance | 0.0 | $\Omega / \mathrm{sq}$ |
| 2 | RCON $^{1}$ | Resistance of contacts | 0 | $\Omega$ |
| 3 | NC1 (NC) | Number of ohmic contacts at node 1 |  |  |
| 4 | NC2 | Number of ohmic contacts at node 2 |  |  |
| 5 | DL | Delta length | 0 | m |
| 6 | DW | Delta width | 0 | m |
| 7 | POLY | Keyword to identify the resistor as non-linear polynomial |  |  |

1. RCON is taken into account in the Resistor computation if $\mathrm{NC} 1, \mathrm{NC} 2$ are defined.

## Level 3

This corresponds to the RC Wire model.

Please see the "RC Wire" on page 148.

## Level 4

This is the default model inside Accusim. Parameters:
Table 4-4. Resistor Model—Level 4 Parameters

| Nor. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | RSH | Sheet resistance | 50.0 | $\Omega / \mathrm{sq}$. |
| 2 | LNARROW | Delta length | 0 | m |
| 3 | WNARROW | Delta width | 0 | m |

Table 4-4. Resistor Model—Level 4 Parameters

| Nor. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 4 | NARROW | Delta | 0 | m |
| 5 | R | Multiplier (used for Monte Carlo) | 1 |  |

The device value is computed as follows:

$$
R=R S H \times \frac{L_{e f f}}{W_{e f f}}
$$

where:

- $\mathrm{L}_{\text {eff }}=\mathrm{L}-$ LNARROW if LnARrow is specified, or $\mathrm{L}_{\text {eff }}=\mathrm{L}-$ NARROW if NARROW is specified.
- $\mathrm{W}_{\text {eff }}=\mathrm{W}-$ WNARROW if wnarrow is specified, or $\mathrm{W}_{\text {eff }}=\mathrm{W}$ - NARROW if NARROW is specified.

Level 6
This corresponds to the Diffusion resistor model.

Please see the "Diffusion Resistor" on page 154.

## Capacitor

```
Cxx NP NN [MOD[EL]=MNAME] [DCCUT] [VAL] [M=VAL] [L=VAL] [W=VAL]
+ [T[EMP]=VAL] [DTEMP=VAL] [TC1=T1] [TC2=T2] [TC3=T3] [IC=VAL]
+ [STATISTICAL=0|1]
Cxx NP NN POLY VAL {COEF} [TC1=T1] [TC2=T2] [TC3=T3] [M=VAL]
+ [CTYPE=VAL] [IC=VAL] [STATISTICAL=0|1]
Cxx NP NN [VALUE=|C=]{EXPR} [ACDERFUNC=0|1] [RESTORE_CAUSALITY=0|1]
+ [TC1=T1] [TC2=T2] [TC3=T3] [CTYPE=VAL] [STATISTICAL=0|1]
```


## Parameters

- $x x$

Capacitor name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- VAL

Value of the capacitor in Farads (voltage independent value). This value can be assigned directly or via the .PARAM command. Optional if a capacitor model is used. For more information, see ".PARAM" on page 778.

- poly

Keyword to identify the capacitor as non-linear polynomial.

## Note

Instead of using the poly keyword, you can also specify parameters VC1=value and $\mathrm{VC} 2=\mathrm{value} . \mathrm{VC1}$ is equivalent to the first parameter of the polynomial array, VC2 is equivalent to the second parameter of the polynomial array.

- VALUE $=\{E X P R\} \mid \mathbf{C}=\{$ EXPR $\}$

Keyword indicating that the capacitor has a functional description. This enables the instantiation of a frequency-dependent capacitor to be simulated in all analysis modes (AC, Transient, SST and MODSST). The expression can make use of the FREQ keyword to specify frequency. A typical application is to model skin-effect, with C varying according to SQRT(FREQ).

- ACDERFUNC=0|1

Derivative of function selector for AC analysis only. For voltage or current dependent capacitors, the derivatives of the value with respect to the voltage are dumped in the matrix by default. Setting acderfunc to 0 forces Eldo to ignore these derivatives when generating the matrix. The specification on the device overrides any global setting by options acderfunc (set by default) or noacderfunc.

- RESTORE_CAUSALITY=0|1

Having a purely real impedance that varies with the square root of frequency is not physically realizable. It would be non-causal. Thus when modeling a physical resistance, specifying a variation as the square root of frequency can be interpreted by Eldo as either:

- specifying the module of the impedance (default, or Restore_CAUSALIty=0), or
- specifying the real part of the impedance, and Eldo computes the imaginary part (RESTORE_CAUSALITY=1)
- MNAME

Model name. This is useful in combination with Monte Carlo analysis.

- DCCUT

For DC, TRAN, MODSST analyses, the DCcut device is assumed to be a normal capacitance of VAL Farads. For .AC, .SSt, .SStac, .SStnoise and .SStxf analyses, the DCCUT device corresponds to an open circuit in DC and a short circuit for all other frequencies.

- coef

Polynomial coefficients used to calculate the voltage dependency of the capacitance. The value of the capacitor is computed as:

$$
\text { Capacitor Value }=V A L+C 1 \times V+C 2 \times V^{2}+\ldots+C n \times V^{n}
$$

where V is the voltage across the capacitor.

- $\mathrm{M}=\mathrm{VAL}$

Multiplier representing the number of parallel devices in the simulation. The total capacitor value will be multiplied by this parameter value. Default value=1.0.

The device is first evaluated without the $m$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values wand are not affected. Models are chosen depending on input w and $\mathbf{L}$, if required. Options minc, maxl, minw, maxw, and so on, do not apply either, since they check the input values of w and L .

Note
Using an M factor value less than 1 could lead to simulating devices that cannot be physically realized.

- $\mathrm{L}=\mathrm{VAL}$

Capacitor length (Effective $\mathrm{L}=\boldsymbol{L} \times \boldsymbol{S H R I N K}$ ), see model parameter list where the shrink factor is listed.

- $\mathrm{W}=\mathrm{VAL}$

Capacitor width (Effective $\mathrm{W}=\boldsymbol{W} \times$ SHRINK), see model parameter list where the shrink factor is listed.

- $\boldsymbol{T}[E M P]=$ VAL

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- DTEMP=VAL

Temperature difference between the device and the rest of the circuit, in degrees Celsius. Default value is 0.0.

Note
TeMP and dTemp are mutually exclusive. If both are specified, the last one is used.

- TC1, TC2, TC3

First, Second, and Third order temperature coefficients. Default values are zero.

- IC=VAL

Sets the initial guess for the voltage across the capacitor prior to a transient analysis. To use this option, the UIC parameter must also be present in the . TRAN statement. For more information, see ".TRAN" on page 911.

- STATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .

- CTYPE=VAL

Determines the calculation mode for capacitors defined by polynomial or functional expressions (VALUE=\{EXPR $\}$ ). The default value is 0 .

When стYpe=0, the current out of the bias-dependent capacitor is computed as $\mathrm{I}(\mathrm{C})=\mathrm{dQ} / \mathrm{dt}$, with Q computed by integrating the equation $\mathrm{dQ}=\mathrm{C} \times \mathrm{dV}$. Default.

When $\mathbf{C T Y P E}=1$, the current out of the bias-dependent capacitor is also computed as $\mathrm{I}(\mathrm{C})=\mathrm{dQ} / \mathrm{dt}$, but with Q computed as $\mathrm{Q}=\mathrm{C} \times \mathrm{V}$.
When CTYPE=2, a charge equation is used, the current out of the bias-dependent capacitor is computed as $\mathrm{I}(\mathrm{C})=\mathrm{dQ} / \mathrm{dt}$, with Q provided by the expression and not computed.
Eldo will check dependencies of the capacitor value. When the value of the capacitor does not depend on the bias of the pins of the device, the СтYPE=1 formulation is normally more appropriate. In this case Eldo will behave on the device as if $\mathbf{~ с т Y P E ~}=1$ had been set, unless option noautoctype is set, or unless ctype is explicitly set on the device.

## Note

The IC=VAL statement cannot be given immediately after a model name, for instance in the following example: Cxx np nn mname IC=value, mname would not be considered as a model name, but as the value of the capacitor, and Eldo would look for a parameter named mNAME. Ensure any other parameter is inserted preceding the IC parameter, for example: Cxx $\mathbf{N P}$ nn miname $\mathbf{~ T C 1 = 0 ~}$ IC=value

## Note

If the value of the capacitor is defined by a poly or value expression, the actual value will be recalculated at each timestep during transient analysis. If an AC analysis is performed however, the value is calculated only once in the DC analysis, and then considered to be static.

## Examples

c1 n3 n4 0.5pf

Specifies a 0.5 pF capacitor c1 placed between nodes n 3 and n 4 .

```
c1 n3 n7 poly 5p 0.1p 0.07p 0.004p
```

Specifies a 5 pF capacitor c1 placed between nodes n 3 and n 7 , whose voltage dependency is described by the 3rd order polynomial:

$$
\text { value }=5 p+0.1 p \times V+0.07 p \times V^{2}+0.004 p \times V^{3}
$$

where V is the voltage across the capacitor.

```
c2 n1 n2 cval
.param cval=0.4p
```

Specifies a capacitor c 2 of value cval placed between nodes n 1 and n 2 . The capacitor value is declared globally in the .PARAM command.

```
c1 1 2 value={2n*v(3,4)*i(v5)}
```

Specifies a capacitor c1 between nodes 1 and 2 whose value is described by the expression in curly brackets.

Dynamic current calculation (стчег) example:

```
v10 2 0 sin (0 1 100meg)
r10 2 0 1
v1 1 0 1
c1 1 0 value = {1.0e-9 * v(2,0)}
.tran 1n 100n
.print tran i(v1)
.plot tran i(v1)
.end
```

Eldo will issue a warning that $\mathbf{C T Y P E}=1$ is emulated on device C 1 .

## Capacitor Model Syntax

.MODEL MNAME C[AP] [\{PAR=VAL\}]

The Eldo capacitor model supports Monte Carlo analysis whereby the tolerance of the capacitor can be defined to vary in a correlated or un-correlated way over a number of simulation runs.

## Note

$\square$Specifying sCALM=val in the .model statement in a capacitor model overrides the global scaling specified by the .OPTION SCALM=val statement.

Table 4-5. Capacitor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C $^{1}$ or <br> SCALE[C] | Capacitance multiplier | 1 |  |
| 2 | CDEF | Value of capacitor if value isn't given in instance | 0 | F |
| 3 | LOT | Correlated device tolerance (Monte Carlo analysis) |  |  |
| 4 | DEV | Uncorrelated device tolerance (Monte Carlo analysis) |  |  |
| 5 | POLY ${ }^{2}$ | Keyword to identify the capacitor as non-linear <br> polynomial |  |  |
| 6 | POLYV | Used to change the formula used for computing the C <br> value | 2 |  |
| 7 | REVSP | Used to change the formula used for computing the C <br> value | 0 |  |
| 8 | TC1 | First order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-1}$ |
| 9 | TC2 | Second order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-2}$ |
| 10 | TC3 | Third order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-3}$ |
| 11 | CAPSW | Sidewall fringing capacitance | $\mathrm{Fm}^{-1}$ |  |
| 12 | COX ${ }^{3}$ | Bottomwall capacitance | 0 | $\mathrm{Fm}^{-2}$ |
| 13 | DEL | Small decrement in dimensions of a device structure <br> on both ends of L and W due to process effects <br> (undercutting) | 0 |  |
| 14 | DI | Relative dielectric constant | 0 | $\mathrm{~m}^{2}$ |
| 15 | SHRINK ${ }^{4}$ | Shrink factor for physical dimensions | 1 |  |
| 16 | THICK | Insulator thickness | Default capacitor length | 0 |
| 17 | L | m | 0 |  |

Table 4-5. Capacitor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 18 | W | Default capacitor width | 0 | m |
| 19 | DTEMP | Temperature difference of capacitor with respect to the <br> rest of the circuit | 0 |  |
| 20 | SCALM | Model parameter scaling factor. This overrides the <br> global sCALM value defined using the .oprIon <br> command. | 1 |  |
| 21 | TNOM | Nominal temperature | 27 | ${ }^{\circ} \mathrm{C}$ |

1. Is computed as $L_{e f f} \times W_{e f f} \times C_{o x e f f}+2 \times\left(L_{e f f}+W_{e f f}\right) \times C A P S W$
2. Instead of using the POLY keyword, you can also specify parameters VC1=value and VC2=value. VC1 is equivalent to the first parameter of the polynomial array, VC2 is equivalent to the second parameter of the polynomial array.
3. $\boldsymbol{C}_{\text {oxeff }}$ is computed as $E P S O \times D I / T O X$ if TOX is specified, $E P S O \times D I / T H I C K$ if THICK is specified (TOX and THICK are synonymous), $E P S O \times D I / 0.5 \mu$ otherwise.
4. Effective value of length $=(L \times S H R I N K-2 \times D E L \times S C A L E M)$

Effective value of width $=(W \times S H R I N K-2 \times D E L \times S C A L E M)$
If cox is not specified, it is computed as:
$C O X=\frac{\varepsilon o \times D I}{T H I C K}$ if $\boldsymbol{D I}$ is specified, $C O X=\frac{\varepsilon x}{T H I C K}$ otherwise,
where $\varepsilon o$ is the permittivity of air, and $\varepsilon o x$ is the permittivity of the oxide.


Tip: For detailed information on usage of poly, revsp, and polyv parameters, see "POLY usage" on page 129.

## Examples

```
*MODEL definition
.model cmodel cap lot=2%
*main circuit
c3 1 s cmodel 0.5pf
```

Specifies a 0.5 pF capacitor c 3 placed between the nodes 1 and s , using the .moder command to define its parameters for a Monte Carlo analysis.

```
c1 1 2 cmodel1 tc1=25e-3 m=2 dtemp=10
.model cmodel1 c cox=1e-12 capsw=1e-12 del=0.01
+ l=1 w=1 tc1=50e-6 tc2=0
```

These are valid instance and model cards from which nominal capacitance may be evaluated from a simplified equation (no SHRINK or scale factors):

$$
\begin{aligned}
& \text { Capacitance }= \\
& \{(L-2 \times D E L) \times(W-2 \times D E L) \times C O X+2 \times(L-2 \times D E L) \times(W-2 \times D E L) \times C A P S W\}
\end{aligned}
$$

In the following example, the bias independent value of the capacitor will be computed as if there were no poly parameters. Then, the active value of the capacitor will be equal to the product of the "bias-independent-value" multiplied by the polynomial expression.

```
.MODEL model_name C TC1=1 POLY
+ <list_of_parameter_values> TC2=value
```

polyv example:
Assuming the model:

```
.MODEL FOO C POLY P1 P2 P3.. Pn
C pin1 pin2 Foo <cinst>
```

And, for example, $V=V($ pin1 $)-V(\operatorname{pin} 2)$ :

- If polyv=2: the value of $C$ will be computed as:
$C=\langle$ cinst $\rangle *(P 1+P 2 * V+P 3 * V * V+\ldots)$
- If polyv $\neq 2$ : the value of $C$ will be computed as:

$$
C=\langle\text { cinst }\rangle *(1+P 1 * V+P 2 * V * V+\ldots)
$$

## Inductor

```
Lxx NP NN [MOD [EL]=MNAME] [DCFEED] [VAL] [M=VAL1] [T [EMP]=VAL] [DTEMP=VAL]
+ [IC=VAL3] [TC1=T1] [TC2=T2] [TC3=T3] [R=VAL4] [STATISTICAL=0|1]
Lxx NP NN POLY VAL \{LN\} [IC=VAL] [R=VAL] [TC1=T1] [TC2=T2] [TC3=T3]
+ [STATISTICAL=0|1]
LXX NP NN [VALUE=|L=]\{EXPR\} [ACDERFUNC=0|1] [RESTORE_CAUSALITY=0|1]
\(+[\mathbf{R}=\mathrm{VAL} \mid \mathbf{R}\) VALUE=EXPR|R TABLE \(\{f \mathrm{fal}\) rval\}]
+ [TC1=T1] [TC2=T2] [TC3=T3] [LTYPE=VAL] [STATISTICAL=0|1]
Lxx \{port_list\} KMATRIX=data_block [STATISTICAL=0|1]
Lxx \{port_list\} RELUCTANCE=(\{rn, cn, valn\}) <options> [STATISTICAL=0|1]
Lxx \{port_list\} RELUCTANCE \{FILE="file"\} <options> [STATISTICAL=0|1]
```


## Parameters

- $x x$

Inductor name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- VAL

Inductor value in Henrys. This value can be assigned directly or via the . PARAM command. Optional if an inductor model is used. For more information, see ".PARAM" on page 778.

- POLY

Keyword to identify the inductor as non-linear polynomial.

## Note

Instead of using the poly keyword, you can also specify parameters VC1=value and $\mathrm{VC} 2=\mathrm{value}$. VC1 is equivalent to the first parameter of the polynomial array, VC2 is equivalent to the second parameter of the polynomial array.

- VALUE $=\{E X P R\} \mid L=\{E X P R\}$

Keyword indicating that the inductor has a functional description. This enables the instantiation of a frequency-dependent inductor to be simulated in all analysis modes (AC, Transient, SST and MODSST). The expression can make use of the FREQ keyword to specify frequency. A typical application is to model skin-effect, with L varying according to SQRT(FREQ).

- ACDERFUNC=0|1

Derivative of function selector for AC analysis only. For voltage or current dependent inductors, the derivatives of the value with respect to the voltage are dumped in the matrix by default. Setting acderfunc to 0 forces Eldo to ignore these derivatives when generating the matrix. The specification on the device overrides any global setting by options acderfunc (set by default) or noacderfunc.

- RESTORE_CAUSALITY=0|1

Having a purely real impedance that varies with the square root of frequency is not physically realizable. It would be non-causal. Thus when modeling a physical resistance, specifying a variation as the square root of frequency can be interpreted by Eldo as either:

- specifying the module of the impedance (default, or restore_Causality=0), or
- specifying the real part of the impedance, and Eldo computes the imaginary part
(RESTORE_CAUSALITY=1)
For transient simulation, Eldo fits R with a rational function $H(s)$, where $s=j \times w$. In the first case, $H(s)$ is found so that its module best fits $R(f)$. In the second case, $H(s)$ is found so that its real part best fits $\mathrm{R}(\mathrm{f})$.
There is however a better way to approach frequency dependent resistor and inductance modeling, which is to specify both the real part $(\mathrm{R}(\mathrm{f})$ ) and imaginary part ( $\mathrm{jw} \times \mathrm{L}(\mathrm{f})$ ) of impedance, with a relationship that maintains causality: this is possible using the syntax:

```
Lxx N1 N2 value={expr} R value={expr}
```

- MNAME

Model name. This is useful in combination with Monte Carlo analysis. If mOD= is specified, Eldo will look for a .model card. If not specified, Eldo will look for a parameter named foo.

- DCFEED

For DC, TRAN, MODSST analyses, the DCFeed device is assumed to be a normal inductance of val Henrys. For .ac, .sst, .sstac, .sstnoise and .sstxf analyses, the dCFEED device corresponds to a short circuit in DC and an open circuit for all other frequencies.

- LN

Coefficients of a polynomial used to calculate the inductances. The inductor is expressed as a function of the current I across the element. The value of the inductance is computed as:

$$
\text { Inductor Value }=V A L+\mathrm{L} 1 \times I+\mathrm{L} 2 \times I^{2}+\ldots+\mathrm{Ln} \times I^{n}
$$

where $I$ is the current through the inductor.

- $I C=V A L$

Sets the initial 'guess' for the current through the inductor prior to a transient analysis. To use this option the UIC parameter must also be present in the .TRAN statement.

- $\mathrm{M}=\mathrm{VAL}$

Multiplier representing the number of parallel devices in the simulation. Default value=1.0.
The device is first evaluated without the $m$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values w and $\mathbf{L}$ are not affected. Models are chosen depending on input wand $\mathbf{L}$, if required. Options mind,

MAXL, MINW, MAXW, and so on, do not apply either, since they check the input values of w and L .

Note
Using an M factor value less than 1 could lead to simulating devices that cannot be physically realized.

- $\mathbf{T}[\mathbf{E M P}]=\mathrm{VAL}$

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- $\mathbf{D T E M P}=\mathrm{VAL}$

Temperature difference between the device and the rest of the circuit, in degrees Celsius.
Default value is 0.0.
Note
TEMP and DTEMP are mutually exclusive. If both are specified, the last one is used.

- TC1, TC2, TC3

First, Second, and Third order temperature coefficients.

- $\quad R=V A L \mid R$ VALUE $=\{E X P R\} \mid R$ TABLE $=\{$ fval rval $\}$
$\mathbf{R}$ is a resistor that is added in series with inductor $\mathbf{L}$. Default value is 0.0 . When
R VALUE $=\{\operatorname{EXPR}\}$ is specified, it indicates that the resistor has a functional description, enabling a frequency-dependent resistor. The expression can make use of the freq keyword to specify frequency. When $\mathbf{R}$ table is specified, it indicates that the resistor accepts a table description, with pairs of frequency and resistor values specified. This device is supported for all analyses (DC, AC, TRAN, SST, MODSST, and so on).


## Note



If the value of the inductor is defined by a poly or value expression, the actual value will be recalculated at each timestep during transient analysis. If an AC analysis is performed however, the value is calculated only once in the DC analysis, and then considered to be static.

- STATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .

- LTYPE=VAL

Determines the calculation mode for inductors defined by functional expressions (VALUE=\{EXPR\}). The default value is 0 .

When Ltype $=0$, the voltage across the inductor is computed as $\mathrm{V}=\mathrm{dFlux} / \mathrm{dt}$, with Flux computed by integrating the equation dFlux $=I \times d V$. Default.

When $\operatorname{LTYpe}=1$, the voltage across the inductor is also computed as $\mathrm{V}=\mathrm{dFlux} / \mathrm{dt}$, but with Flux computed as Flux $=\mathrm{I} \times \mathrm{V}$.

When LTYPe=2, a flux equation is used, the voltage across the inductor is computed as $\mathrm{V}=\mathrm{dFlux} / \mathrm{dt}$, with Flux provided by the expression and not computed.

- KMATRIX=data_block

K-element for modeling the parasitic inductive effect of general 3-D interconnects. It is described by a multi-port inductor record and the matrix values are provided through a data block (.DATA). Values in the matrix are reluctance values, not inductance values.
Eldo will check that:

- the K-element has an even number of nodes
- the kmatrix has a valid value and a data block exists
- the matrix is positive definite
- all diagonal terms are defined and have positive values
- there is no duplicate entry and no term is defined below the diagonal
- port_list

List of ports for K-element, specified as pairs of electrical node names, each defining an interconnect branch.

- reluctance

Keyword indicates that reluctance (inverse inductance) will be provided. The unit for reluctance is inverse Henry $\left(\mathrm{H}^{-1}\right)$. The presence of this keyword indicates that all tokens between Lname and the RELUCTANCE keyword should be interpreted as node names.

- RELUCTANCE $=(\{r n, \mathrm{cn}, \mathrm{valn}\})$

Inline form of reluctance specification for modeling the parasitic inductive effect of general 3-D interconnects. $\mathrm{rn}, \mathrm{cn}$, valn is a triplet of values describing the reluctance between two interconnect branches.
rn integer value of branch \#1; integer refers to the pair of nodes that define branch \#1
cn integer value of branch \#2; integer refers to the pair of nodes that define branch \#2
valn reluctance value between branch \#1 and branch \#2 $\left(\mathrm{H}^{-1}\right)$

- FILE="file"

External file format of reluctance specification for modeling the parasitic inductive effect of general 3-D interconnects. The data files should contain three columns of data. Each row should contain an ( $\mathrm{r}, \mathrm{c}$, val) triplet separated by spaces. The r, c, and val values may be expressions surrounded by single quotes. Multiple files may be specified to allow the
reluctance data to be spread over several files if necessary. The files should not contain a header row.

- <options>

Valid options for reluctance specification include:

```
SHORTALL=yes|no
```

causes all inductors to be converted to short circuits, and all reluctance matrix values to be ignored.

IGNORE_COUPLING=yes|no
causes all off-diagonal terms to be ignored (i.e., set to zero).

## Examples

$$
11 \text { n13 n8 5u }
$$

Specifies a $5 \mu \mathrm{H}$ inductor 11 placed between nodes n 13 and n 8 .

```
l1 n10 n5 poly 7u 0.15 0.03
```

Specifies a $7 \mu \mathrm{H}$ inductor 11 placed between nodes n 10 and n 5 , whose current dependency is described by a second order polynomial of the form:

$$
\text { value }=7 \mu+0.15 \times I+0.003 \times I^{2}
$$

where $I$ is the current across the inductor.

```
13 n1 n2 lval
.param lval=0.6ph
```

Specifies an inductor named 13 of value lval placed between nodes n 1 and n 2 . The inductor value is declared globally in the .PARAM command.

```
1112 value \(=\{2 u * \mathbf{v}(3,4) * i(v 5)\}\)
```

Specifies an inductor 11 between nodes 1 and 2 whose value is described by the expression in curly brackets.
K-element example:

```
L_ThreeNets (a,1) (1,2) (2,a_1) (b,4) (4,5) (5,b_1) (c,7) (7,8)
(8,c_1) KMATRIX=StartK
.DATA StartX
+ PORT1 PORT2 VALUE
+ 1 1 103e9
+ 4 -34.7e9
+ 7 -9.95e9
+4 4 114e9
+4 7 -34.7e9
+7 103e9
+ 2 103e9
+ 5 -34.7e9
+ 8 -9.95e9
+ 5 114e9
+ 8 -34.7e9
```

```
+8 8 103e9
+ 3 103e9
+ 6 - -34.7e9
+ 9 -9.95e9
+6 6 114e9
+ 6 9 -34.7
+ 9 103e9
```

Another K-element example using the alternate inline syntax:

```
L_ThreeNets a 1 1 2 2 a_1 b 4 4 5 5 b_1 c 7 7 8 8 c_1
+ RELUCTANCE=(
+ 1, 1, 103e9,
+ 1, 4, -34.7e9,
+ 1, 7, -9.95e9,
+ 4, 4, 114e9,
+ 4, 7, -34.7e9,
+ 7, 7, 103e9,
+ 2, 2, 103e9,
+ 2, 5, -34.7e9,
+ 2, 8, -9.95e9,
+ 5, 5, 114e9,
+ 5, 8, -34.7e9,
+ 8, 8, 103e9,
+ 3, 3, 103e9,
+ 3, 6, -34.7e9,
+ 3, 9, -9.95e9,
+ 6, 6, 114e9,
+ 6, 9, -34.7e9,
+ 9, 9, 103e9 )
```

Another K-element example using the alternate external file syntax:

```
L_ThreeNets a 1 1 2 2 a_1 b 4 4 5 5 b_1 c 7 7 8 8 c_1 RELUCTANCE
+ FILE="reluctance.dat"
```

where the file reluctance.dat contains the three columns of data.

## Inductor Model Syntax

```
.MODEL MNAME IND [{PAR=VAL}]
```

The inductor model provided with Eldo is, as with the capacitor model described before, used in conjunction with a Monte Carlo analysis whereby the tolerance of the inductor can be defined to vary in a correlated or uncorrelated way during a number of simulation runs.

Table 4-6. Inductor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | L or <br> SCALEL | Inductance multiplier | 1 |  |
| 2 | LOT | Correlated device tolerance (Monte Carlo analysis) |  |  |
| 3 | DEV | Uncorrelated device tolerance (Monte Carlo analysis) |  |  |

Table 4-6. Inductor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 4 | POLY ${ }^{1}$ | Keyword to identify the inductor as non-linear <br> polynomial |  |  |
| 5 | POLYV | Used to change the formula used for computing the L <br> value | 2 |  |
| 6 | REVSP | Used to change the formula used for computing the L <br> value | 0 |  |
| 7 | TC 1 | First order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-1}$ |
| 8 | TC 2 | Second order temperature coefficient | 0 | ${ }^{\circ} \mathrm{C}^{-2}$ |
| 9 | LDEF | Inductor value to be provided to the inductor instance <br> if no instance parameters are specified | 0 | H |
| 10 | TNOM | Nominal temperature | 27 | ${ }^{\circ} \mathrm{C}$ |

1. Instead of using the POLY keyword, you can also specify parameters VC1=value and $\mathrm{VC} 2=\mathrm{value} . \mathrm{VC1}$ is equivalent to the first parameter of the polynomial array, VC2 is equivalent to the second parameter of the polynomial array.

Tip: For detailed information on usage of poly, revsp, and polyv parameters, see "POLY usage" on page 129.

## Examples

The following specifies a 0.5 pH inductor placed between the nodes 1 and s , using the . MODEL command to define the parameters for a Monte Carlo analysis.

```
*MODEL definition
.model lmodel ind lot=2%
*main circuit
l1 1 s lmodel 0.5ph
```

In the following, the scalel parameter multiplies the inductance value given in the instantiation. Therefore this inductor will have a value of 6 pH .

```
*MODEL definition
.model lmodel ind scalel=3
*main circuit
l1 1 s lmodel 2ph
```

In the following, the value of L 1 will be 1 uH . This shows how the inductor .model card provides the value to the inductor instance when no instance parameters are specified,

```
.MODEL foo IND LDEF=1u
L1 1 2 MOD=foo
```


## Coupled Inductor

Kxx Lyy Lzz KVAL [KR=KRVAL]

## Parameters

- xx

Name of the coupled inductor.

- yy, zz

Names of the two inductors building $\mathrm{Kxx}_{\mathrm{x}}$.

- kVAL

Coupling coefficient where usual value is $-1 \leq K V A L \leq+1$. If a value outside this range is specified, Eldo will generate the warning message:

```
unusual coefficient ... <KVAL>
```

- $\mathrm{KR}=\mathrm{KRVAL}$

KR is a resistor that is coupled with the coupled inductor K . Default value is 0.0.
Mutual inductance is given by: $M x x=K V A L \times \sqrt{L y y \times L z z}$
Mutual resistance is given by: $R x x=K R V A L \times \sqrt{R y y \times R z z}$
where:
$L y y, L z z, R y y, R z z$ are the inductance and resistance values of the corresponding impedance.
Usually $-1 \leq K V A L \leq+1$, otherwise a warning is generated.
When a coupling resistance coefficient $K R V A L$ is specified on the K statement, $\mathrm{R}=\mathrm{Rval}$ must be specified on the corresponding impedance statements, otherwise $K R V A L$ is ignored.

Figure 4-1. Coupled Inductor


## Example

$$
\begin{array}{llll}
17 & 4 & 3 & 0.7 \mathrm{~m} \\
\mathbf{1 8} & 5 & 9 & 0.4 \mathrm{~m} \\
\mathbf{k} 12 & 17 & 18 & 0.2
\end{array}
$$

Specifies the coupling of inductors 17 and 18 , with a coupling coefficient of 0.2 . The coupling element, or transformer, is given the symbol k12.

## RC Wire

```
Rxx N1 N2 MNAME [[R=]VAL] [TC1=VAL] [TC2=VAL] [C=VAL] [CRATIO=VAL]
+ [L=VAL] [W=VAL] [M=VAL] [T[EMP]=VAL] [DTEMP=VAL] [SCALE=VAL]
+ [STATISTICAL=0|1]
```


## Parameters

- xx

RC wire name.

- N1, N2

Names of the RC wire nodes.

- MNAME

Model name.

- [R=]VAL

Resistance value in $\Omega$. Default is the value of res as specified in the .model statement. Specifying $\mathrm{R}=$ is optional, the value can be specified without it.

- TC1=VAL

First order temperature coefficient of the resistance in ${ }^{\circ} \mathrm{C}^{-1}$. Default is the value of $\mathbf{T C 1 R}$ as specified in the .model statement.

- $\quad$ C2 $=\mathrm{VAL}$

Second order temperature coefficient of the resistance in ${ }^{\circ} \mathrm{C}^{-2}$. Default is the value of $\mathbf{T C 2 R}$ as specified in the .model statement.

- $\mathbf{C = V A L}$

Capacitance connected from node n2 to BULK in Farads. See the "RC Wire Model Syntax" on page 150 . Default is the value of cap as specified in the .model statement. The c value is split between the two pins of the resistor. The model parameter CRATIO controls the splitting.

- CRATIO=VAL

Controls the splitting of the c value between the two pins of the resistor. $\mathbf{C \times C R A T I O}$ is the value which will be attached to node N 1 , while $\mathrm{C} \times(1.0-\mathrm{CRATIO})$ will be attached to node N2. Default is 0.0 . This parameter cannot be specified for an instance. It can only be specified on the .model statement.

- $\mathrm{L}=\mathrm{VAL}$

Resistor length in meters. Default is the value of L as specified in the .model statement.

- $\mathbf{w}=$ val

Resistor width in meters. Default is the value of $\mathbf{w}$ as specified in the .model statement.

- $\mathbf{M}=\mathrm{VAL}$

Multiplier to simulate parallel resistors. Default is 1 .

The device is first evaluated without the $m$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values w and $\mathbf{L}$ are not affected. Models are chosen depending on input wand $\mathbf{L}$, if required. Options mind, maxi, minw, maxw, and so on, do not apply either, since they check the input values of w and L .

## Note

Using an M factor value less than 1 could lead to simulating devices that cannot be physically realized.

- $\mathbf{T}[$ EMP $]=\mathrm{VAL}$

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- DTEMP=VAL

Temperature difference between the device and the rest of the circuit, in degrees Celsius. Default value is 0.0 .

Note
temp and dtemp are mutually exclusive. If both are specified, the last one is used.

- SCALE=VAL

Element scale factor for resistance and capacitance. Default is 1 .

- STATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .

## Note

In order to select the RC Wire model, the level parameter must be set to level=3 in
the model mName.
The model name mname is mandatory for the RC wire model. At least one parameter must be specified in this model. If this is not the case, Eldo interprets the definition as a normal resistor.
The same model name MNAME cannot be used for both a normal resistor model and an RC Wire model.

## Example

$$
\mathbf{r} 1 \mathrm{n} 3 \mathrm{n} 4 \bmod 1 \mathrm{tc} 1=0.001
$$

Specifies an RC wire placed between nodes $n 3$ and $n 4$. The first order temperature coefficient is defined to be 0.001 .

## RC Wire Model Syntax

.MODEL MNAME R[ES] [PAR=VAL]

The RC wire model can be made to behave like a simple resistor or an elementary transmission line. This is achieved by specifying an optional capacitor from node $n 2$ to BULK or ground. The bulk node functions as a ground plane for the wire capacitance. The wire is described by a drawn length and width. The resistance of the wire is the effective length multiplied by the RSH parameter then divided by the effective width.

Table 4-7. RC Wire Model Parameters

| Nr. | Name | Description | Default | Units |
| :---: | :---: | :---: | :---: | :---: |
| 1 | LEVEL | Must be set to 3 to select RC wire model |  |  |
| 2 | RDEF | Value of resistor. This value has priority over values computed from L and W | $1 \times 10^{3}$ | $\Omega$ |
| 3 | POLY ${ }^{1}$ | Keyword to identify the resistor as non-linear polynomial |  |  |
| 4 | POLYV | Used to change the formula used for computing the R value | 2 |  |
| 5 | REVSP | Used to change the formula used for computing the R value | 0 |  |
| 6 | BULK | Default reference node for capacitance | 0 |  |
| 7 | CAP | Default capacitance | 0 | F |
| 8 | CAPSW | Sidewall fringing capacitance | 0 | $\mathrm{Fm}^{-1}$ |
| 9 | COX | Bottomwall capacitance | 0 | $\mathrm{Fm}^{-2}$ |
| 10 | DI | Relative dielectric constant | 0 |  |
| 11 | DLR | Difference between drawn length and actual length | 0 | m |
| 12 | DW | Difference between drawn width and actual width | 0 | m |
| 13 | L | Default length of wire | 0 | m |
| 14 | RES | Default resistance | 0 | $\Omega$ |
| 15 | RSH | Sheet resistance/square | 0 |  |
| 16 | SHRINK | Shrink factor | 1 |  |
| 17 | TC1C | 1st order temperature coefficient for capacitance | 0 | ${ }^{\circ} \mathrm{C}^{-1}$ |
| 18 | TC2C | 2nd order temperature coefficient for capacitance | 0 | ${ }^{\circ} \mathrm{C}^{-2}$ |
| 19 | TC1R | 1st order temperature coefficient for resistance | 0 | ${ }^{\circ} \mathrm{C}^{-1}$ |
| 20 | TC2R | 2nd order temperature coefficient for resistance | 0 | ${ }^{\circ} \mathrm{C}^{-2}$ |
| 21 | THICK | Dielectric thickness | 0 | m |

Table 4-7. RC Wire Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 22 | W | Default width of wire | 0 | m |
| 23 | KF | Flicker noise coefficient | 0.0 |  |
| 24 | AF | Flicker noise exponents | 1.0 |  |
| 25 | WEEXP |  | 0.0 |  |
| 26 | LEEXP |  | 0.0 |  |
| 27 | FEXP |  | 1.0 |  |

1. Instead of using the POLY keyword, you can also specify parameters VC1=value and VC2=value. VC 1 is equivalent to the first parameter of the polynomial array, VC 2 is equivalent to the second parameter of the polynomial array.

## Calculation of Wire Resistance

The element width and length are scaled by the parameters scale and shrink. The model width and length are scaled by the parameters sCalm=x (. option command) and shrink. The effective width and length are calculated from the following equations:

$$
\begin{aligned}
W_{e f f} & =W_{\text {scaled }}-\left(2 \times D W_{\text {eff }}\right) \\
L_{\text {eff }} & =L_{\text {scaled }}-\left(2 \times D L R_{\text {eff }}\right)
\end{aligned}
$$

where:

$$
\begin{aligned}
D W_{e f f} & =D W \times S C A L M \\
D L R_{e f f} & =D L R \times S C A L M \\
L_{\text {scaled }} & =L \times S H R I N K \times S C A L M \\
W_{\text {scaled }} & =W \times S H R I N K \times S C A L M
\end{aligned}
$$

If element resistance $R$ is specified:

$$
R_{e f f}=\frac{R \times S C A L E(\text { element })}{M}
$$

Otherwise, if ( $W_{\text {eff }} \times L_{e f f} \times R S H$ ) is greater than zero, then:

$$
\text { Reff }=\frac{L e f f \times R S H \times S C A L E(\text { element })}{M \times W e f f}
$$

If ( $W_{\text {eff }} \times L_{\text {eff }} \times R S H$ ) is zero, then:

$$
\text { Reff }=\frac{R E S \times S C A L E \text { (element) }}{M}
$$

If AC resistance is specified in the element, then:

$$
R A C e f f=\frac{A C \times S C A L E \text { (element) }}{M}
$$

Otherwise, if RAC is specified in the model, RAC is used:

$$
R A C e f f=\frac{R A C \times S C A L E(\text { element })}{M}
$$

If neither are specified, it defaults to:

$$
\text { RACeff }=\text { Reff }
$$

If the resistance is less than resmin, it is reset to resmin and a warning message is issued.

$$
\text { resmin }=\frac{1}{G M A X \times 1000 \times M}
$$

## Note

REVSP and polyv usage:
If parameter revsp is set to 1 on the .model card, and if polyv is not 2, then the formula for computing the current generated by the Resistor is:
$\mathrm{I}=\mathrm{V} /<$ rinst $>*(1+\mathrm{P} 1 / 2+\mathrm{P} 2 / 3 * \mathrm{~V} * \mathrm{~V} . .$.
which leads to a Resistor of value:
$\mathrm{R}(\mathrm{V})=1 /(\mathrm{dI} / \mathrm{dV})=\langle$ rinst $\rangle /(1+\mathrm{P} 1 . \mathrm{V}+\mathrm{P} 2 * \mathrm{~V} * \mathrm{~V})$

## Calculation of Wire Capacitance

The effective length is the scaled drawn length less $2 \times D W_{\text {eff }}$. $L_{\text {eff }}$ represents the effective length of the resistor from physical edge to physical edge. $D W_{\text {eff }}$ is the distance from the drawn edge of the resistor to the physical edge of the resistor. The effective width is the same as the width used in the resistor calculation.

$$
\begin{aligned}
L_{e f f} & =L_{\text {scaled }}-\left(2 \times D W_{e f f}\right) \\
W_{e f f} & =W_{\text {scaled }}-\left(2 \times D W_{e f f}\right)
\end{aligned}
$$

If the element capacitance C is specified:

$$
C A P_{e f f}=C \times S C A L E \times M
$$

Otherwise, the capacitance is selected from $L_{\text {eff }}, W_{\text {eff }}$ and $C O X$.

$$
C A P_{e f f}=M \times S C A L E \times\left[L_{e f f} \times W_{e f f} \times C O X+2.0 \times\left(W_{e f f}+L_{e f f}\right) \times C A P S W\right]
$$

If COX is not specified, but the model parameter THICK is not zero, then:

$$
C O X=\frac{D I \times \varepsilon o}{T H I C K}
$$

if DI is not zero or:

$$
C O X=\frac{\varepsilon o x}{\text { THICK }}
$$

if $\mathrm{DI}=0$, where:

$$
\begin{aligned}
\varepsilon o & =8.8542149 \times 10^{-12} \frac{F}{\text { meter }} \\
\varepsilon o x & =3.453148 \times 10^{-11} \frac{F}{\text { meter }}
\end{aligned}
$$

If only model capacitance CAP is specified:

$$
C A P_{e f f}=C A P \times S C A L E \times M
$$

## Example

```
.model rmodel r cap=0.5p tc1c=0.01 tc2c=0.05
r2 n1 n2 r rmodel tc1=0.05
```

Specifies an RC wire placed between nodes n 1 and n 2 of model type rmodel. Electrical parameters of the model are defined via the .MODEL command.

## Diffusion Resistor

Pxx N1 N2 [NS] MNAME [L=VAL] [W=VAL] [NB=VAL]

## Parameters

- $x x$

Diffusion resistor name.

- N1, N2, NS

Names of the diffusion resistor nodes.

- MNAME

Model name; name of the associated .model statement.

- $\mathrm{L}=\mathrm{VAL}$

Specifies the resistor length in meters. Default is $1 \mu \mathrm{~m}$.

- $\mathbf{w = V A L}$

Specifies the resistor width in meters.

- $\mathrm{NB}=\mathrm{VAL}$

Specifies the number of bends in the resistor.
Note
The length $L$ must be explicitly specified either on the instance or in the .model command.

## Diffusion Resistor Model Syntax

.MODEL MNAME R[ES] LEVEL=6 [PAR=VAL]
The diffusion resistor model accurately models the effects temperature, applied bias and backbias dependencies of NWell, N+, and P+ resistors.

Table 4-8. Diffusion Resistor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | L | Drawn length of resistor | $-{ }^{1}$ | m |
| 2 | W | Drawn width of resistor | $1 \times 10^{-6}$ | m |
| 3 | NB | Number of bends in the resistor | 0 | - |
| 4 | M | Multiplicity factor | 1.0 |  |

Table 4-8. Diffusion Resistor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 5 | TR,TREF, <br> TNOM | Temperature at which the parameters have been <br> determined | 25 | ${ }^{\circ} \mathrm{C}$ |
| 6 | DTA | Temperature offset of the RDIFF | 0 | ${ }^{\circ} \mathrm{K}$ |
| 7 | TRISE | Alias of DTA resistor element with respect to $\mathrm{T}_{\mathrm{A}}$ | 0 | ${ }^{\circ} \mathrm{K}$ |
| 8 | RSHR | Sheet resistance at $\mathrm{T}=\mathrm{T}_{\mathrm{R}}$ | 1 k | $\Omega / \mathrm{sq}$ |
| 9 | WTOL | Offset between the drawn and effective resistor <br> width | 0 | m |
| 10 | TCR1 | Linear temperature coefficient of the resistor | 0 | ${ }^{\circ} \mathrm{K}^{-1}$ |
| 11 | TCR2 | Quadratic temperature coefficient of the resistor | 0 | ${ }^{\circ} \mathrm{K}^{-2}$ |
| 12 | VPR | Reference Pinch-off voltage | 0 | $\mathrm{~V}^{\prime}$ |
| 13 | SWVP | Coefficient of the width dependence of VP | 0 | $\mathrm{Vm}^{-1}$ |
| 14 | POWER | Voltage exponent | 1.5 | - |
| 15 | VDR | Diffusion voltage at T = $\mathrm{T}_{\mathrm{R}}$ | 1 | $\mathrm{~V}^{2}$ |
| 16 | RINT | Interface resistance at $\mathrm{T}=\mathrm{T}_{\mathrm{R}}$ | $\Omega$ | $\Omega \mathrm{m}^{-1}$ |
| 17 | TCRINTI | Linear temperature coefficient of the interface <br> resistor | 0 | ${ }^{\circ} \mathrm{K}^{-1}$ |

1. The length $L$ must be explicitly specified either on the instance or in the . MODEL command.
[^2]
## Semiconductor Resistor

Pxx N1 N2 NS MNAME [R=VAL] [L=VAL] [CL=VAL] [W=VAL] [CW=VAL] [AREA=VAL]
$+[$ STATISTICAL $=0 \mid 1]$

## Parameters

- $x x$

Semiconductor resistor name.

- N1, N2, NS

Names of the semiconductor resistor nodes.

- MNAME

Model name.

- $\mathbf{R}=\mathrm{VAL}$

Specifies the resistance. (If $\mathrm{R}=0$, or if R is not specified, then automatic calculations are used.)

- $\mathrm{L}=\mathrm{VAL}$

Specifies the resistor length. Default is $10 \mu \mathrm{~m}$.

- $\mathrm{CL}=\mathrm{VAL}$

Specifies the contact offset length. Default is $2 \mu \mathrm{~m}$.

- $\mathbf{w = V A L}$

Specifies the resistor width. Default is $2 \mu \mathrm{~m}$ (Defw from .model statement).

- $\mathrm{CW}=\mathrm{VAL}$

Specifies the contact offset width. Default is $0 \mu \mathrm{~m}$.

- AREA=VAL

Specifies the area of the resistor.

- StATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .

## Semiconductor Resistor Model Syntax

. MODEL MNAME TYPE [PNAME=PVAL]

- TYPE

This must be either RN or RP.
The figure below illustrates the cross-sectional view of a diffused semiconductor resistor.

Figure 4-2. Cross-Sectional View of Diffused Resistor


RN


RN

Table 4-9. Semiconductor Resistor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | TC1 | First temperature coefficient of bulk | 0.0 | $\Omega^{\circ} \mathrm{C}^{-1}$ |
| 2 | TC2 | Second temperature coefficient of bulk | 0.0 | $\Omega^{\circ} \mathrm{C}^{-1}$ |
| 3 | CTC1 | First temperature coefficient of contact hole | 0.0 | $\Omega^{\circ} \mathrm{C}^{-1}$ |
| 4 | CTC 2 | Second temperature coefficient of contact hole | 0.0 | $\Omega^{\circ} \mathrm{C}^{-1}$ |
| 5 | RSH | Sheet resistance of bulk | 10 | $\Omega / \mathrm{sq}$ |
| 6 | CRSH | Sheet resistance of contact hole | 10 | $\Omega / \mathrm{sq}$ |
| 7 | A1 | Contact coefficient 1 | 1.0 |  |
| 8 | B1 | Contact coefficient 2 | 1.0 |  |
| 9 | DEFW | Default width | $2 \times 10^{-6}$ | m |

Table 4-9. Semiconductor Resistor Model Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 10 | NARROW | Narrowing due to side etching | 0.0 | m |
| 11 | IS | Saturation current | $1 \times 10^{-14}$ | A |
| 12 | RS | Ohmic resistance | 0.0 | $\Omega$ |
| 13 | M | Grading coefficient | 0.5 |  |
| 14 | N | Emission coefficient | 1.0 |  |
| 15 | TT | Transition time | 0.0 | s |
| 16 | CJO | Zero bias junction capacitance | 0.0 | F |
| 17 | PB | Junction built-in potential | 1.0 | V |
| 18 | EG | Energy gap | 1.1 | eV |
| 19 | XTI (PT) | Saturation current temperature exponent | 3.0 |  |
| 20 | KF | Flicker noise coefficient | 0.0 |  |
| 21 | AF | Flicker noise exponent | 1.0 |  |
| 22 | FC | Forward bias non-ideal junction capacitance <br> coefficient | 0.5 |  |
| 23 | BV | Reverse breakdown voltage | $\bullet$ | V |
| 24 | IBV | Current at BV | $1 \times 10^{-03}$ | A |

## Semiconductor Resistor Model Equations

## Resistance R calculation

$$
\begin{aligned}
& R=R B L K+2 R C \\
& R=R B 0+R B 1+2 R C=R(T N O M)
\end{aligned}
$$

## Contact Resistance RC

$$
R C=C R S H \cdot \frac{A 1}{W^{B 1}}=R C(T N O M)
$$

## Bulk Resistance

$$
R B L K=R B 0+R B 1
$$

- Resistance for bulk part

$$
R B 0=\frac{L-2 C L-N A R R O W}{W-N A R R O W+2 C W} \cdot R S H=R B 0(T N O M)
$$

- Resistance near the contact

$$
R B 1=\frac{2 C L-N A R R O W}{W-N A R R O W+2 C W} \cdot C R S H=R B 1(T N O M)
$$

## Temperature Effects

$$
\begin{aligned}
& R(T E M P)=R B 0(T E M P)+R B 1(T E M P)+2 R C \\
& R B 0(T E M P)=R B 0(T N O M) \\
& \cdot\left[1+T C 1 \cdot(T E M P-T N O M)+T C 2 \cdot(T E M P-T N O M)^{2}\right] \\
& R B 1(T E M P)=R B 1(T N O M) \\
& \cdot\left[1+C T C 1 \cdot(T E M P-T N O M)+C T C 2 \cdot(T E M P-T N O M)^{2}\right]
\end{aligned}
$$

- Noise Model Sources

$$
i_{n R s}=\left[\frac{4 k T}{R}\right]^{\frac{1}{2}}
$$

## Diode Model Equations

$$
\begin{aligned}
T & =T E M P+273.15 \\
T_{0} & =T N O M+273.15
\end{aligned}
$$

Internal DC Model Parameters

$$
\begin{aligned}
& \text { RATIO }=\frac{T-T_{0}}{T_{0}} \\
& q=1.6 \times 10^{-19} \quad k=1.38 \times 10^{-23} J^{\circ} K^{-1} \\
& V_{t}=\frac{k T}{q} \quad V_{t 0}=\frac{k T_{0}}{q} \\
& I_{s}=I S \cdot A R E A \cdot\left[\frac{T}{T_{0}}\right]^{P T}\left[e^{\left[\frac{(E G)(R A T I O)}{V_{t}}\right]}\right] \\
& I_{b v}=I B V \cdot A R E A
\end{aligned}
$$

$$
V_{C R I T}=V_{t 0} \ln \left[\frac{V_{t 0}}{1.414 \cdot I S}\right]
$$

$\boldsymbol{V}_{\boldsymbol{C R I T}}$ is used as a starting point for DCOP.

## Internal Charge Related Model Parameters

$$
\begin{aligned}
& E g=1.16-0.000702\left[\frac{T^{2}}{T+1108}\right] \\
& E g_{r e f}=1.1150877 \\
& V_{r e f}=V t(T) \cdot\left(\frac{E G(T N O M)}{V t(T N O M)}-\frac{E G(T)}{V t(T)}+3 \ln \frac{T}{T N O M}\right) \\
& P_{b}=P B\left[\frac{T}{T_{0}}\right]-V_{r e f} \\
& C_{j}=C J O \cdot A R E A \cdot\left[1+M\left\{0.0004\left(T-T_{0}\right)+\left[1-\left(\frac{P_{b}}{P B}\right)\right]\right\}\right]
\end{aligned}
$$

## DC Current Source Definitions

## $\boldsymbol{V}_{\boldsymbol{d}}=($ Internal Anode Voltage $)-($ Internal Cathode Voltage $)$

When BV is not specified by the user:

- If $V_{d} \geq-5 N \cdot V_{t}$

$$
I_{d}=I_{s}\left[e^{\left[\frac{V_{d}}{(N)\left(V_{t}\right)}\right]}-1\right]+(\text { GMIN }) V_{d}
$$

- If $V_{d}<-5 N \cdot V_{t}$

$$
I_{d}=I_{s}\left(e^{-5}-1\right)+\left[\frac{I_{s}}{(N)\left(V_{t}\right)}\right] e^{-5}\left[V_{d}+5 N \cdot V_{t}\right]+(G M I N) V_{d}
$$

When BV is specified by the user:

- If $V_{d} \geq-5 N \cdot V_{t}$

$$
I_{d}=I_{s}\left[e^{\left[\frac{V_{d}}{(N)\left(V_{t}\right)}\right]}-1\right]+(G M I N) V_{d}
$$

$\boldsymbol{X}_{\boldsymbol{b} \boldsymbol{v}}$ is an internally generated voltage which facilitates the continuous representation of diode current.

- If $X_{b v} \leq V_{d}<-5 N \cdot V_{t}$

$$
I_{d}=I_{s}\left(e^{-5}-1\right)+\left[\frac{I_{s}}{N \cdot V_{t}}\right] e^{-5}\left[V_{d}+5 N \cdot V_{t}\right]+(G M I N) V_{d}
$$

- If $V_{d}<X_{b v}$

$$
\begin{aligned}
& I_{d}=I_{s}\left(e^{-5}-1\right)+\left[\frac{I_{s}}{N \cdot V_{t}}\right] e^{-5}\left[V_{d}+5 N \cdot V_{t}\right] \\
& -e^{-5}\left(I_{s}\right)\left[e^{\left[\frac{-\left(V_{d}-X_{b v}\right)}{N \cdot V_{t}}\right]}-1\right]+(\text { GMIN }) V_{d}
\end{aligned}
$$

## Diode Diffusion Capacitance

$$
C_{d 2}=T T\left[\frac{d\left(I_{d}\right)}{d\left(V_{d}\right)}\right]
$$

## Diode Depletion Capacitance

- If $V_{d}<F C \cdot P_{b}$

$$
C D S=C S 0 \cdot\left(1-\frac{V_{d}}{P_{b}}\right)^{-M}
$$

where $C S 0=\frac{1}{2} \cdot \frac{R-2 R C}{R S H} \cdot W^{2} \cdot C J 0$

- If $V_{d} \geq F C \cdot P_{b}$

$$
C_{d 1}=C_{j}\left[(1-F C)^{-M}\left[\frac{M(1-F C)^{-M}}{P_{b}(1-F C)}\right]\left(V_{d}-F C \cdot P_{b}\right)\right]
$$

## Small Signal Model Equations

$$
\begin{aligned}
& C_{d}=C_{d 1}+C_{d 2} \\
& g_{d}=\frac{d\left(I_{d}\right)}{d\left(V_{d}\right)}
\end{aligned}
$$

$$
r_{d}=\frac{1}{g_{d}}
$$

## Diode Model Noise Source Equations

- Resistance Generated Noise

$$
i_{n r s}=\left[\frac{4 k T}{R_{s}}\right]^{\frac{1}{2}}
$$

- Current Source Generated Shot and Flicker Noise

$$
\begin{aligned}
& i_{n F}=\left[\frac{K F \cdot I_{d}^{A F}}{R_{s}}\right]^{\frac{1}{2}} \\
& i_{n s}=\left(2 q I_{d}\right)^{\frac{1}{2}}
\end{aligned}
$$

## Transmission Line

```
Txx NAP NAN NBP NBN [ZO=VAL1] TD=VAL2 [STATISTICAL=0|1]
Txx NAP NAN NBP NBN [z0=VAL1] F=VAL3 [NL=VAL4] [STATISTICAL=0|1]
```

1. For Lossy dispersive transmission lines, please refer to "Lossy Transmission Line" on page 165.

## Parameters

- xx

Transmission line name.

- NAP

Positive A terminal of the transmission line.

- NAN

Negative A terminal of the transmission line.

- NBP

Positive B terminal of the transmission line.

- NBN

Negative B terminal of the transmission line.

- TD=VAL2

Transmission delay in seconds.

- $\quad \mathbf{F}=\mathrm{VAL} 3$

Frequency in Hertz.

- $\mathbf{z 0}=$ VAL1

Characteristic impedance in $\Omega$. Default value is $50 \Omega$. Optional.

- $\mathbf{N L = V A L} 4$

Number of wavelengths at frequency $\mathbf{F}$ required for a wave to propagate down the line. Default value is 0.25 . Optional.

The above parameters can also be assigned via the .PARAM command.

- Statistical=o|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .
The relationship between the $\mathbf{T D}, \boldsymbol{F}$ and $\mathbf{N L}$ values is given by:

$$
T D=\frac{1}{F} \times N L
$$

## Examples

$$
\text { t1 } 1234 \mathbf{z o}=220 \text { td=111ns }
$$

Specifies a transmission line t 1 between nodes 1 (+ve A) and 2 (-ve A) and nodes 3 (+ve B) and 4 (-ve B), with a characteristic impedance of $220 \Omega$. The transmission delay of the line is 111 ns .

```
t2 1 2 3 4 zo=220 f=2.25meg
```

Specifies the same transmission line as above, but in terms of a frequency for a quarter wavelength (as NL defaults to 0.25 ).

```
t3 1 2 3 4 zo=220 f=4.5meg nl=0.5
```

Specifies the same transmission line as above, but in terms of a frequency for half a wavelength.

## Lossy Transmission Line

LDTL (Lossy Dispersive Transmission Line) is a model implemented in Eldo to simulate transmission lines. It is dedicated for the simulation of lossy coupled uniform lines, also including dispersive effects. This model can be used in all analysis modes (DC, AC, Transient, SST, SSTNOISE, or MODSST). To specify the line parameters to the LDTL model, four different inputs are available:

1. the first level corresponds to $\mathrm{R}, \mathrm{L}, \mathrm{C}$ and G matrices,
2. the second level uses a file at XFX output format as input to specify the line parameters,
3. the third level corresponds to the electrical parameters for a single line,
4. the fourth level corresponds to the geometrical and physical parameters for a single stripline or up to two coupled microstrip lines.

Ways of instantiation are shown on the following pages. You can also instantiate an LDTL model by using a model of MODFAS type (see ".MODEL" on page 723) directly in the parameter list. This model must be specified at the end of the instantiation line and can contain any parameter. For each level, an example is provided in the directory
\$MGC_AMS_HOME/examples/tlines/LDTL_model.

## Level 1

```
Yxx LDTL [PIN:] P1...PN [REFin] PN+1...P2N REFout
+ [PARAM: [LEVEL=1] [LENGTH=val] [SAVEFIT=val] [M=VAL]
+ [R(i)=val] [L(i,j)=val] [C(i,j)=val] [G(i,j)=val] [FR1=val]]
```

The first level is dedicated to the simulation of an infinite number of coupled transmission lines. The Maxwell matrices ( $\mathrm{R}, \mathrm{L}, \mathrm{C}$ and G ) are used to describe the line system.

## Parameters

- xx

Transmission line name.

- P1...PN

The N nodes at one end of the line system for a system consisting of N lines.

- Refin

Optional reference node for input signal, used to simulate differential lines.

- $\mathrm{PN}+1 . . . \mathrm{P} 2 \mathrm{~N}$

The N nodes at the other end of the line system. The line number i in the line system connects the nodes Pi and $\mathrm{PN}+\mathrm{i}$.

- REFout

Reference node for output signal. If Refin is not specified, then both sides of the line system have the same reference plane.

- Length=val

Geometric length of the line system. Default value is 1 m . If LENGTh=0, Eldo uses the default value.

- LEVEL=1

Keyword to specify the input format. Value 1 specifies the "R,L,G,C matrices" format. Default value is 1 .

- SAVEFIT=val

SAVEFIT $=1 \Rightarrow$ Saves the initialization of the transmission line model (in the file
circuit_name.fit), in order to speed up the following simulations of the same netlist. Default value is 0 .

- $\mathbf{M}=\mathrm{val}$

Device multiplier. Simulates the effect of multiple devices in parallel. In effect the current value is multiplied by m. Default is 1 . . option ymfact must be selected in order for this option to work.

- $\quad \mathbf{R}(\mathrm{i})=\mathrm{val}$

Value of the (i,i) element per unit length of the resistance matrix: R. Default values are $50 \Omega \mathrm{~m}^{-1}$.

- $L(i, j)=v a l$

Value of the ( $\mathrm{i}, \mathrm{j}$ ) element per unit length of the inductance matrix: L. Default values $1 \times 10^{-6} \mathrm{Hm}^{-1}$ for the self inductance and 0 for the mutual inductances.

- $\quad \mathbf{C}(i, j)=v a l$

Value of the ( $\mathrm{i}, \mathrm{j}$ ) element per unit length of the capacitance matrix: C. Default values $1 \times 10^{-9} \mathrm{Fm}^{-1}$ for the self capacitance and 0 for the mutual capacitances.

- $G(i, j)=v a l$

Value of the $(\mathrm{i}, \mathrm{j})$ element per unit length of the conductance matrix: G. Default values are $0 \mathrm{Sm}^{-1}$.

- FR1=val

Frequency at which dispersion starts (only affects resistance). Default: no dispersion will be considered.

If for a line only $R(1)$ is specified, this value is used for all lines. Specification of the Transmission line matrix parameter can be done in one of the following ways:

- Complete matrix of coefficients consisting of $\mathrm{N} \times \mathrm{N}$ values.
- Only the upper (or lower) triangular matrix because of the matrix symmetry.
- Only the first row (or column) of the matrix. This is normally sufficient if all lines in the system have the same width and spacing.


## Example

Circuit name: YLDTL_levell_example.cir. Three coupled lines defined by R, L, C and G matrices:

```
Y1 LDTL 2 3 4 4 0 5 6 7 0
+ param: LEVEL=1 length=0.677
+ R(1)=15 L (1, 1)=418n C (1, 1)=94p G (1, 1)=0.02p
+ R(2)=15 L (2, 2)=418n C (2, 2)=94p G (2, 2)=0.02p
+C(1,2)=-22p C (2,3)=-22p
+ L(1, 2)=125n L (2, 3)=125n
+ R(3)=15 L (3,3)=418n C (3,3)=94p G (3, 3)=0.02p
```

Notice that $\mathrm{C}(1,2)$ and $\mathrm{C}(2,3)$ are both negative. This is because Eldo uses the Maxwell matrix. The capacitance matrices are based on the admittance matrix of the capacitances between the conductors. The negative values in the capacitance matrix are due to the sign convention for admittance matrices.

Same example using a . MODEL in the instantiation:

```
Y1 LDTL 2 3 4 0 5 6 7 0
+ param: LEVEL=1 length=0.677
+ model:level1_mod
.model level1_mod MODFAS R(1)=15
+ L(1,1)=418n C (1,1)=94p G (1,1)=0.02p
+ R(2)=15 L (2,2)=418n C (2,2)=94p G (2,2)=0.02p
+C(1,2)=-22p C (2,3)=-22p
+ L(1,2)=125n L (2,3)=125n
+ R(3)=15 L (3,3)=418n C (3,3)=94p G(3,3)=0.02p
```


## Level 2

```
Yxx LDTL [PIN:] P1...PN [REFin] PN+1...P2N REFout
+ [PARAM: [LEVEL=2] [LENGTH=val] [SAVEFIT=val]
+ [XFX_IDF=val] [FP=val] [MULTIDEBYE=val]]
```

The second level uses a file of XFX output format as input to specify the line parameters. This level is dedicated to the simulation of an infinite number of coupled transmission lines.

## Parameters

The description of the global parameters (pins, Length and savefit) is as specified for the Level=1 format. Level 2 specific parameters are shown below.

- LEVEL=2

Keyword to specify the input format. Value 2 specifies the XFX format. Default value is 1 .

- XFX_IDF=val

Index relative to the XFX file name. If Xfx_IDF=val, Eldo will search for the file $X F X \_v a l . t l p$. Eldo searches for the specified file in a specific order, see "Search path priorities" on page 694.

- $\mathbf{F P}=$ val

Polarization frequency to control dispersive effect on the conductance (see "Technical Precision" on page 173). Default: $1.6 \times 10^{9}$.

- multidebye=val
val=1 specifies the use of multi-pole debye model to model the dispersive effect on the conductance (recommended for modeling PCB-type dielectrics). val $=0$, this model is not used. (see "Technical Precision" on page 173). Default: 1.


## Example

Circuit name: YLDTL_level2_example.cir. Two coupled lines defined by an XFX output file:

```
Y1 LDTL 1 2 3 4 0
+ param: LEVEL=2 length=0.1 xfx_idf=12
```

Same example using a .model in the instantiation:

```
Y1 LDTL 1 2 3 4 0
+ param: model:level2_mod
.model level2_mod MODFAS LEVEL=2 length=0.1 xfx_idf=12
```

The parameter $\mathrm{xfx} \mathrm{x}_{\mathrm{i}} \mathrm{idx}=12$ is a reference to the file $X F X_{-}$12.tlp containing the line information generated by XFX. Here is an example of such a file:


## Level 3

```
Yxx LDTL [PIN:] P1 [REFin] P2 REFout
+ [PARAM: [LEVEL=3] LENGTH=val] [SAVEFIT=val]
+ [ZC=val] [VREL=val] [TD=val] [L=val] [C=val] [R=val] [FR1=val] [M=val]]
```

The third level corresponds to the electrical parameters for a single line only.

## Parameters

The description of the global parameters (pins, Length and Savefit) is as specified for the LEVEL=1 format. Level 3 specific parameters are shown below.

- LEVEL=3

Keyword to specify the input format. Value 3 specifies the electrical format. Default value is 1 .

- $\mathbf{z c}=$ val

Characteristic impedance ( $\Omega$ ). If this value is not specified, it is calculated with the values of L and C .

- Vrel=val

Relative velocity. If this value is not specified, it is calculated with the values of L and C .

- TD=val

Delay for Length (implies total delay calculated is Length $\times$ td). If not specified, calculated.

- $\mathrm{L}=$ val

Inductance per unit length. Default value: $1 \times 10^{-6} \mathrm{Hm}^{-1}$.

- $\mathrm{C}=$ val

Capacitance per unit length. Default value is: $1 \times 10^{-9} \mathrm{Fm}^{-1}$.

- $\mathbf{R}=$ val

Linear resistance. Default value is $50 \Omega \mathrm{~m}^{-1}$.

- $\quad$ FR1=val

Frequency (Hz) at which dispersion starts (only affects resistance). Default: no dispersion will be considered.

- M=val

Device multiplier. Simulates the effect of multiple devices in parallel. In effect the current value is multiplied by m. Default is 1 . . option ymfact must be selected in order for this option to work.
You can either specify directly the line parameters $\mathbf{R}, \mathbf{L}$ and $\mathbf{c}$, or use any combination of electrical parameters ( L and C can be computed with electrical parameters, see "Technical Precision" on page 173).

## Example

Circuit name: YLDTL_level3_example.cir. One dispersive line defined by electrical parameters:

```
Y1 ldtl 1 2 0
+ param: LEVEL=3 length=100 R=1
+ ZC=50 VREL=0.66 FR1=100Meg
```

Same example using a .model in the instantiation:

```
Y1 ldtl 1 2 0
+ param: LEVEL=3 length=100 R=1
+ ZC=50 model: level3_mod
.model leve3_mod MODFAS VREL=0.66 FR1=100Meg
```


## Level 4

```
Yxx LDTL [PIN:] P1 [REFin] P2 REFout
+ [PARAM: [LEVEL=4] [LENGTH=val [SAVEFIT=val]
+ [DLEV=val] [PLEV=val] [ER=val] [H=val] [W=val] [T=val]
+ [RHO=val] [TAND=val] [H1=val] [FP=val] [H2=val] [S=val]
+ [THICKNESS=val] [DISPERSIVE=val] [USE_ER=val] [M=val] [MULTIDEBYE=val]]
```

The fourth level corresponds to the geometrical parameters specification for microstrip line and stripline. Up to two coupled microstrip lines are allowed and only one single stripline can be taken into account. The structure of these transmission lines is illustrated in Figure 4-4 (coupled pair of microstrip lines) and Figure 4-5 (stripline).

## Parameters

The description of the global parameters (pins, length and savefit) is as specified for the level=1 format. Level 4 specific parameters are shown below.

- LEVEL=4

Keyword to specify the input format. Value 4 specifies the geometrical and physical format. Default value is 1 .

- DLEV=val

Type of line: 1 for microstripline; 2 for stripline. Default is 1 .

- PLEV=val

Type of equations: 0 uses the equations from the references (1) and (2), 1 for simplified equations. Default is 0 .

- $\mathbf{E R}=\mathrm{val}$

Dielectric relative permittivity. Default value is 9.8 (alumina).

- $\mathrm{H}=\mathrm{val}$

Dielectric thickness (m). Default value is $400 \times 10^{-6} \mathrm{~m}$.

- W=val

Conductor width. Default value is $50 \times 10^{-6} \mathrm{~m}$.

- $\mathbf{T}=\mathrm{val}$

Conductor thickness. Default value is $5 \times 10^{-6} \mathrm{~m}$.

- RHO=val

Conductor resistivity. Default value is $17 \times 10^{-9} \Omega \mathrm{~m}$ (copper).

- TAND=val

Dielectric loss tangent. Default value is 0 .

- $\mathrm{H} 1=\mathrm{val}$

Conductor height, only for stripline configuration. Default value is $197.5 \times 10^{-6} \mathrm{~m}$.

- $\mathbf{F P}=$ val

Polarization frequency to control dispersive effect on the conductance (see "Technical Precision" on page 173). Default: $1.6 \times 10^{9}$.

- $\mathrm{H} 2=\mathrm{val}$

Height between dielectric and a possible cover plate. Only for coupled microstrip configuration. Default: 0.0, means that no cover plate is taken into account.

- $\mathbf{s = v a l}$

Spacing between the two conductors. Default = conductor width value (W). Only for coupled microstrip configuration.

- thickness=val

Take into account effect of finite strip thickness if val=1. Default: 0 . Only for coupled microstrip configuration.

- DISPERSIVE=val

Take into account dispersive effect if val=1. Default: 0 . Only for coupled microstrip configuration.

- USE_ER=val

Use directly the dielectric relative permittivity (ER) to compute the characteristic impedance ( Zc ) if val=1. Otherwise (if val=0), an effective relative permittivity will be calculated and used in the Zc computation (see Technical Precision, "Level 4" on page 175 for details). Default: 1 .

- $\mathbf{M = v a l}$

Device multiplier. Simulates the effect of multiple devices in parallel. In effect the current value is multiplied by m. Default is 1. . option ymfact must be selected in order for this option to work. Only used for stripline (DLEV=2).

- MULTIDEBYE=val
val=1 specifies the use of multi-pole debye model to model the dispersive effect on the conductance (recommended for modeling PCB-type dielectrics). val $=0$, this model is not used. (see "Technical Precision" on page 173). Default: 1.


## Note

When plev=0 and dlev=2, it is only possible to describe an off-centered microstrip line with the equations based on reference [1].

## Examples

Circuit name: YLDTL_level4_example.cir. A microstrip line based on equations from reference [1].

```
Y1 LDTL 1 2 0
+ param: LEVEL=4 length=10 PLEV=0 DLEV=1
+ h=400u w=50u t=5u rho=17E-09 er=9.8
```

Circuit name: YLDTL_level4_example2.cir. Symmetric pair of coupled microstrip lines, including finite strip thickness and dispersive effects.

```
Y1 LDTL 1 2 0 3 4 0
+ param: LEVEL=4 length=10e-3 PLEV=1 DLEV=1
+ h=635u w=88u t=2u s=90u h2=935u
+ rho=1.72E-08 tand=0.01 thickness=1
+ dispersive=1
```

Same example using a .model in the instantiation:

```
Y1 LDTL 1 2 0 3 4 0
+ param: LEVEL=4 length=10 PLEV=1 DLEV=1
+ h=635u w=88u model:level4_mod
.model level4_mod MODFAS t=2u s=90u h2=935u
+ rho=1.72E-08 tand=0.01 thickness=1
+ dispersive=1
```


## Error Message Treatment

A general problem which causes many errors is incorrect time delay values. These values are calculated by multiplying the L and C matrices. Negative or null time delay values can cause errors in the model. To avoid the simulation being stopped, here follows some advice on how to avoid errors. The error message is shown, together with advice on avoiding this type of error.

```
ERROR model Yxx : no time-delay in the transmission line(s), check your
input parameters.
```

This means that some value(s) of the L or C matrix (or both) are bad: the diagonal of $\mathrm{L} \times \mathrm{C}$ matrix presents null value(s) (see "General Equation for Delay" on page 173). It can appear when some off-diagonal term(s) of the C or L matrix are too large. Normally the coupling effect
on L and C decreases when the distance between the two concerned lines increase. That means: $|\mathrm{C}(1,2)|$ should be larger than $|\mathrm{C}(1,3)|$.

```
ERROR model Yxx: Non physical line model (negative time delay). Check C
and/or L matrices off-diagonal terms.
```

This message appears only for coupled transmission line models. It means that the time-delay of at least one line of the model is negative. So this modelization is not a physical one.

This means the diagonal of $\mathrm{L} \times \mathrm{C}$ matrix presents negative value(s) (see "General Equation for Delay" on page 173). It can appear when some off-diagonal term(s) of the C or L matrix are too large. Normally the coupling effect on $L$ and $C$ decreases when the distance between the two concerned lines increase. That means: $|C(1,2)|$ should be larger than $|C(1,3)|$.

```
ERROR model Yxx : the diagonal of C is non-strictly-dominant : you should
have Sum{|(C(i,j)|} < |C(i,i)| (i != j)
```

This means some off-diagonal terms of the C matrix are too large. Therefore, the sum of all the off-diagonal terms of one line of the matrix is not lower than the diagonal term of the line: the strictly-dominant property is not verified. Such a property is required for the model.

```
WARNING model Y1 : negative diagonal value(s) : R[1][1]
```

This warning means that the value $\mathrm{R}[1][1]$ is negative. Therefore, you have to check the parameters of the model instantiation according to the LEVEL used (see Technical Precision).

## Technical Precision

Here follows some technical information about the use of the Yxx LDTL model.

## General Equation for Delay

The time-delay ( $T d$ ) of a single transmission line is computed as follows:

$$
T d=\text { Length } \times \sqrt{L C}
$$

When we have a n-coupled transmission line model, the time-delay matrix is computed as follows ( $L, C$ and $T d m$ are matrices):

$$
T d m=\operatorname{Length} \times \operatorname{diag}(L \times C)
$$

$T d m$ is a diagonal matrix. The $n^{\text {th }}$ element of the diagonal is the time-delay of the $n^{\text {th }}$ line of the model. Therefore, these diagonal values must be positive.

## Level 1

To introduce skin effects in the line model (loss that is proportional to the square root of frequency), you just have to specify the FRl parameter. Then the resistivity value will be frequency dependent:

$$
R=R(i) \times\left(1+(1+i) \sqrt{\frac{f}{F R 1}}\right) \text { for the } \boldsymbol{i}^{t h} \text { transmission line } .
$$

## Level 2

Here the skin effect is introduced by the parameter Rs:

$$
R=R_{D C}+R_{S} \times(1+i) \sqrt{4 \pi f}
$$

You can also introduce frequency dependent conductance by using the parameters $G s$ and $f p$ (polarization frequency: FP parameter). The conductance dispersive effect can be modeled in two ways according to the multidebye parameter:

- One-pole debye model (multidebye=0)

The dispersive effect is obtain according to the following equation:

$$
G=G_{D C}+G_{S} \times \frac{i 2 \pi f \times 2 \pi f p}{i 2 \pi f+2 \pi f p}
$$

- Multi-pole debye model (multidebye=1)

By using this option, we build a complex frequency-dependent capacitance matrix:

$$
C(\omega)=C_{i n f}+f(j \omega) C_{d}
$$

Therefore, line conductance per unit length becomes:

$$
Y(j \omega)=G_{D C}+(j \omega) C_{i n f}+(j \omega) f(j \omega) C_{d}
$$

where: $C_{\text {inf }}=C-\alpha G_{s}$ and $C_{d}=\beta G_{s} ; C$ and $G s$ are the user-defined matrices.
with $\alpha=\frac{\ln \left(\frac{\omega_{2}^{2}+\omega_{0}^{2}}{\omega_{1}^{2}+\omega_{0}^{2}}\right)}{4 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)}$ and $\beta=\frac{\ln \left(10^{8}\right)}{2 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)}$
Finally, the function $f(j \omega)=\frac{\ln \left(\frac{\omega_{2}+j \omega}{\omega_{1}+j \omega}\right)}{\ln \left(10^{8}\right)}$ which is fitted with 15 real poles.
Note: $\omega_{0}=2 \pi f_{p}, \omega_{1}=10^{4}, \omega_{2}=10^{12}, \omega=2 \pi f$ and $f p$ the polarization frequency ( FP parameter).

## Level 3

As already described, you can either specify directly the line parameters $\mathbf{R}$, $\mathbf{L}$ and $\mathbf{c}$, or use any combination of electrical parameters. In order to discard redundant parameter sets we use the following equations:

Table 4-10. LDTL Level 3 Parameter Combinations

| Input Parameters | Equations |
| :--- | :--- |
| Zc, VREL | $C=\frac{1.0}{Z c \times V R E L \times C l i g h t}, L=\frac{Z c}{V R E L \times C l i g h t}$ |
| Zc, TD | $L=\frac{T D}{Z c}, L=Z c \times T D$ |
| TD, C | $L=\frac{T D^{2}}{V R E L^{2} \times C l i g h t^{2} \times C}$ |
| VREL, C | $C=\frac{T D^{2}}{L}$ |
| TD, L | $C=\frac{1.0}{V R E L^{2} \times C l i g h t^{2} \times L}$ |
| VREL, L | default values for $L$ and $C$ |
| any other |  |

$$
\text { Clight }=3 \times 10^{8} \mathrm{~ms}^{-1}(\text { the speed of light })
$$

The skin effect is introduced by the parameter $\operatorname{FR} 1$ :

$$
R=R \times\left(1+(1+i) \sqrt{\frac{f}{F R 1}}\right)
$$

## Level 4

Only two transmission line configurations can be described with this input format: microstrip line and stripline. The following figures provides the structure of these transmission lines. Figure 4-3 and Figure 4-4 provide the structure for a single and covered pair of microstrip models, Figure 4-5 provides the structure for a stripline.

Figure 4-3. Microstrip Line Structure


Figure 4-4. Covered Pair Microstrip Line Structure


Figure 4-5. Stripline Structure


The plev parameter allows the use of two sorts of equation: reference equations (plev=0) and simplified equations (plev=1). Provided here is the reference formulation.

## For a Single Microstrip Line (DLEV=1)

- From reference (1) (plev=0), we have the following equations:

Capacitance $C=\frac{\sqrt{\mu_{o} \varepsilon_{o} e r}}{Z c}$
Inductance $L=Z c \sqrt{\mu_{o} \varepsilon_{o} e r}$
Resistance $R=\frac{r h o}{w \times t}$
with the characteristic impedance:
$Z c=\frac{\eta_{o}}{2 \sqrt{2} \pi \sqrt{e r+1}} \ln \left\{1+\frac{4 h}{w^{\prime}}\left[\frac{14+8 /(e r)}{11} \times \frac{4 h}{w^{\prime}}+\sqrt{\left(\frac{14+8 / e r}{11}\right)^{2}\left(\frac{4 h}{w^{\prime}}\right)^{2}+\frac{1+1 / e r}{2} \pi^{2}}\right]\right\}$
where:

$$
\begin{aligned}
& w^{\prime}=w+\Delta w^{\prime} \\
& \Delta w^{\prime}=\Delta w\left(\frac{1+1 /(e r)}{2}\right) \\
& \Delta w=\frac{1}{\pi} \ln \left[\frac{4 e}{\sqrt{(t / h)^{2}+\left(\frac{1 / \pi}{w / t+1.1}\right)^{2}}}\right]
\end{aligned}
$$

With $\eta_{o}$, the wave impedance; $\varepsilon_{o}$, the permittivity; and $\mu_{o}$ the permeability of free space.

In reference (1), it is recommended to replace Er by Eeff in the characteristic impedance computation. It is done by specified the parameter USE_ER=0.
for $\frac{w}{h} \leq 1$ :

$$
E_{e f f}=\frac{E r+1}{2}+\frac{E r-1}{2}\left[\left(1+\frac{12 h}{w}\right)^{-0.5}+0.04\left(1-\frac{12 h}{w}\right)^{2}\right]
$$

and for $\frac{w}{h} \geq 1$ :

$$
E_{e f f}=\frac{E r+1}{2}+\frac{E r-1}{2}\left(1+\frac{12 h}{w}\right)^{-0.5}
$$

## For a Symmetric Pair of Coupled Microstrip Lines (DLEV=1)

- From reference (2) (plev=0), we have the following equations:

Capacitance matrix $\left[\begin{array}{cc}\hat{C}+\hat{C_{M}} & -\hat{C_{M}} \\ -\hat{C_{M}} & \hat{C}+\hat{C_{M}}\end{array}\right]$
where: $\hat{C}=\frac{1.0}{v_{p, e} \times Z_{L, e}}$ and $\hat{C_{M}}=\frac{1}{2}\left(\frac{1.0}{v_{p, o} \cdot Z_{L, o}}-\frac{1.0}{v_{p, e} \cdot Z_{L, e}}\right)$

Inductance matrix $\left[\begin{array}{cc}\hat{L} & \hat{L_{M}} \\ \hat{L_{M}} & \hat{L}\end{array}\right]$
where: $\hat{L}=\frac{1}{2}\left(\frac{Z_{L, e}}{v_{p, e}}+\frac{Z_{L, o}}{v_{p, o}}\right)$ and $\hat{L_{M}}=\frac{1}{2}\left(\frac{Z_{L, e}}{v_{p, e}}-\frac{Z_{L, o}}{v_{p, o}}\right)$
Resistance matrix $\left[\begin{array}{ll}\frac{R e+R o}{2} & \frac{R e-R o}{2} \\ \frac{R e-R o}{2} & \frac{R e+R o}{2}\end{array}\right]$
where: $R e=\frac{\ln 10}{10} \cdot \alpha_{c, e} \cdot Z_{L, e}$ and $R o=\frac{\ln 10}{10} \cdot \alpha_{c, o} \cdot Z_{L, o}$
Conductance matrix $\left[\begin{array}{ll}\frac{G e+G o}{2} & \frac{G e-G o}{2} \\ \frac{G e-G o}{2} & \frac{G e+G o}{2}\end{array}\right]$
where: $G e=\frac{\ln 10}{10} \cdot \frac{\alpha_{c, e}}{Z_{L, e}}$ and $G o=\frac{\ln 10}{10} \cdot \frac{\alpha_{c, o}}{Z_{L, o}}$
The indices $e$ and $o$ indicate even and odd mode parameters respectively. The expression of effective relative permittivity, characteristic impedance and attenuation coefficients are given in the single microstrip line description (for more details, see reference (2)). Dispersion is taken into account (when required) in the effective permittivity and characteristic impedance computations (see reference (2)). Therefore, effective parameter matrices ( $\mathrm{R}, \mathrm{L}, \mathrm{C}$ and G ) values change with frequency.

## For a Single Stripline (DLEV=2)

- From reference (1) (pLEv=0), we have the following equations:

Capacitance $C=\frac{\sqrt{\mu_{0} \varepsilon_{0} e r}}{Z_{0}}$
Inductance $L=Z_{0} \sqrt{\mu_{0} \varepsilon_{0} e r}$
Resistance $R_{D C}=\frac{r h o}{w \times t}$
with: $Z_{0}=\frac{\eta_{0}}{\sqrt{e r} \times \frac{C_{1}}{\varepsilon}}$
and:

$$
\begin{aligned}
& \frac{C_{1}}{\varepsilon}=\frac{2 w_{1} / h}{1-s / h-t / h}+\frac{2 w_{1} / h}{1+s / h-t / h}+ \\
& \frac{2}{\pi}\left(\frac{2}{1-t /(h-s)} \ln \left[1+\frac{1}{1-t /(h-s)}\right]+\left(1-\frac{1}{1-t /(h-s)}\right) \ln \left[\frac{1}{(1-t /(h-s))^{2}}-1\right]\right)+ \\
& \frac{2}{\pi}\left(\frac{2}{1-t /(h+s)} \ln \left[1+\frac{1}{1-t /(h+s)}\right]+\left(1-\frac{1}{1-t /(h+s)}\right) \ln \left[\frac{1}{(1-t /(h+s))^{2}}-1\right]\right)
\end{aligned}
$$

where:

$$
\begin{aligned}
& s=h-(2 \times h 1+t) \text {, for a centered stripline } \mathrm{s}=0 \\
& \text { if }\left(\frac{w}{h-t}\right)<0.35 \text { then } w_{1}=\left(\frac{0.07 \times(h-t)+w}{1.2}\right)
\end{aligned}
$$

else $w_{1}=w$
Dispersive effects are introduced according to the value of the geometrical parameters. So the resistivity can be frequency dependent:

$$
R=R_{D C} \times\left(1+(1+i) \times \sqrt{\frac{\frac{f}{r h o}}{\pi \mu_{0} t^{2}}}\right)
$$

You can also introduce frequency dependent conductance by using the parameters $G s$ and $f p$ (polarization frequency: FP parameter). The conductance dispersive effect can be modeled in two ways according to the multidebye parameter:

- One-pole debye model (multidebye=0)

$$
G=\tan d \times C \times \frac{i 2 \pi f \times 2 \pi f p}{i 2 \pi f \times 2 \pi f p}
$$

where $f p$ is the polarization frequency ( FP parameter).

- Multi-pole debye model (multidebye=1)

By using this option, we build a complex frequency-dependent capacitance matrix:

$$
C(\omega)=C_{i n f}+f(j \omega) C_{d}
$$

Therefore, line conductance per unit length becomes:

$$
Y(j \omega)=(j \omega) C_{i n f}+(j \omega) f(j \omega) C_{d}
$$

where: $C_{\text {inf }}=C-\alpha \tan d C$ and $C_{d}=\beta \tan d C ; C$ is the user-defined matrix and tand the dielectric loss tangent parameter.

$$
\text { with } \alpha=\frac{\ln \left(\frac{\omega_{2}^{2}+\omega_{0}^{2}}{\omega_{1}^{2}+\omega_{0}^{2}}\right)}{4 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)} \text { and } \beta=\frac{\ln \left(10^{8}\right)}{2 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)} \text {. }
$$

Finally, the function $f(j \omega)=\frac{\ln \left(\frac{\omega_{2}+j \omega}{\omega_{1}+j \omega}\right)}{\ln \left(10^{8}\right)}$ which is fitted with 15 real poles.
Note: $\omega_{0}=2 \pi f_{p}, \omega_{1}=10^{4}, \omega_{2}=10^{12}, \omega=2 \pi f$ and $f p$ the polarization frequency ( $\mathbf{F P}$ parameter).

## Reference

(1) Transmission Line Design Handbook, Brian C. Wadell, Artech House 1991.
(2) Implementation of Single and Coupled Microstrip Line in APLAC, Luis Costa and Martti Valtonen, CT-33 December 1997.

## Lossy Transmission Line: W Model

The W model is implemented in Eldo to simulate lossy coupled uniform lines including dispersive effects. This model can be used in all analysis modes (DC, AC, Transient, SST, SSTNOISE, or MODSST). The general instantiation of a W model is shown below. Examples are provided in the directory $\$ M G C \_A M S \_H O M E / e x a m p l e s / t l i n e s / W \_m o d e l . ~$

## RLGCfile Form

```
Wxx N=nb_line
+ P1...PN PGNDin PN+1...P2N PGNDout
+ RLGCfile=file_name L=length [FP=val]
+ [MULTIDEBYE=val] [SAVEFIT=val] [COMPAT=val] [FGD=val]
```


## Umodel Form

```
Wxx N=nb_line
+ P1...PN PGNDin PN+1...P2N PGNDout
+ Umodel=model_name L=length [SAVEFIT=val]
```


## RLGCmodel Form

```
Wxx N=nb_line
+ P1...PN PGNDin PN+1...P2N PGNDout
+ RLGCmodel=model_name L=length [FP=val]
+ [MULTIDEBYE=val] [SAVEFIT=val] [COMPAT=val] [FGD=val]
```


## Tabular RLGCmodel Form

```
Wxx P1...PN PGNDin PN+1...P2N PGNDout
+ N=nb_line L=length
+ TABLEMODEL=table_model_name [SAVEFIT=val] [FITTABLEMODEL=val]
```


## Parameters

- xx

W model transmission line name.

- N=nb_line

Number of lines.

- P1...PN

The N nodes at one end of the line system for a system consisting of N lines.

- PGNDin

Reference node for the P1...PN nodes of the line system.

- $\mathrm{PN}+1 \ldots \mathrm{P} 2 \mathrm{~N}$

The N nodes at the other end of the line system. The line number i in the line system connects the nodes Pi and $\mathrm{PN}+\mathrm{i}$.

- PGNDout

Reference node for the $\mathrm{PN}+1 \ldots \mathrm{P} 2 \mathrm{~N}$ nodes of the line system.

- RLGCfile=file_name

Name of the file containing $R, L, C, G, R_{s}$ and $G_{d}$ matrices.

- Umodel=model_name

Name of the transmission line model. This entry allows the use of the U model (see "Lossy Transmission Line: U Model" on page 192) entries in the W model.

- TABLEMODEL=table_model_name

Name of the model containing R, L, C and G tabular matrices description.

- L=length

Geometric length of the system (meter). Default value is 1.0. If $\mathrm{L}=0$, Eldo uses the default value.

- $\quad \mathbf{F P}=$ val

Polarization frequency to control dispersive effect on the conductance. Default: $1.6 \times 10^{9}$.

- MULTIDEBYE=val
val=1 specifies the use of multi-pole debye model to model the dispersive effect on the conductance (recommended for modeling PCB-type dielectrics). val $=0$, this model is not used. Default: 1.
- SAVEFIT=val

If the value is 1 , this option saves the initialization of the transmission line model (in the file circuit_name.fit), in order to speed up the following simulations of the same netlist. Default value is 0 .

- Compat=val

If the value is 1 , it specifies the model used for the dispersive effect is based on conductance, see the formula details of each W model instantiation: "RLGC File Syntax" on page 183 and "RLGC Model Syntax" on page 186. Default value is taken from the global option Compat (if . option compat is specified then compat=1). Note that the mUltidebye parameter priority is higher than COMPAT. If mUltidebye is specified, then the value of сомРАт is zero.

- FGD=val

Cut-off frequency value. Default is zero. Can only be specified in compat mode (COMPAT=1).

- FITTABLEMODEL=val

When set to 1 , it will enable a causal model (admittance and propagation) to be built from non-causal tabulated data. If set to 0 (default), the tabulated data will not be modified to build the model and the built-in models are considered to be causals.

## Examples

## RLGCfile Entry

Circuit name: RLGCfile_example.cir.

```
W1 N=2
+ 1 2 0 3 4 0
+ RLGCfile=2lin.rlgc L=0.97e-3
```

See "Example RLGC file" on page 185.

## Umodel Entry

```
.MODEL unamel U LEVEL=3 ELEV=1 PLEV=1 DLEV=2 NL=1
+ HT=1.0e-4 WD=2.0e-4 TH=5.0e-5 RHO=1.785e-8
W1 N=1 1 0 2 0 Umodel=uname L=1.0e-3
```


## RLGCmodel Entry

W1 N=2 120450 RLGCmodel=model_rlgc L=0.97e-3
Tabular RLGCmodel Entry
W1 i1 i2 0 o1 o2 $0 \mathrm{~N}=2 \mathrm{~L}=0.1$ TABLEMODEL=ex1

## RLGC File Syntax

The RLGC file is a text file, which contains the values of $R, L, C, G, R_{s}$ and $G_{d}$ matrices per unit length. This file is order-dependent, and the order is the following:
$\mathrm{N} \quad$ Number of lines.
$\mathrm{L}_{\mathrm{o}} \quad \mathrm{DC}$ inductance matrix (per unit length).
$\mathrm{C}_{\mathrm{o}} \quad \mathrm{DC}$ capacitance matrix (per unit length).
$\mathrm{R}_{\mathrm{o}} \quad \mathrm{DC}$ resistance matrix (per unit length).
$\mathrm{G}_{\mathrm{o}} \quad \mathrm{DC}$ conductance matrix (per unit length).
$\mathrm{R}_{\mathrm{s}} \quad$ Skin effect resistance matrix (per unit length):

$$
R=R_{o}+(1+i) \sqrt{f} R s
$$

$\mathrm{G}_{\mathrm{d}} \quad$ Dielectric-loss conductance matrix (per unit length). The frequency dependent conductance uses the parameters Gs and $f p$ (polarization frequency: $\operatorname{FP}$ parameter). It can be modeled in two ways according to the multidebye parameter:

- One-pole debye model (multidebye=0)

$$
G=G_{o}+\frac{G_{d}}{2 \pi} \times \frac{i 2 \pi f \times 2 \pi f p}{i 2 \pi f+2 \pi f p}
$$

where $f p$ is the polarization frequency ( $\mathbf{F P}$ parameter).

- Multi-pole debye model (multidebye=1)

By using this option, we build a complex frequency-dependent capacitance matrix:

$$
C(\omega)=C_{i n f}+f(j \omega) C_{d}
$$

Therefore, line conductance per unit length becomes:

$$
Y(j \omega)=G_{o}+(j \omega) C_{i n f}+(j \omega) f(j \omega) C_{d}
$$

where: $C_{i n f}=C-\alpha G_{d}$ and $C_{d}=\beta G_{d} ; C$ and $G s$ are the user defined matrices, with:

$$
\alpha=\frac{\ln \left(\frac{\omega_{2}^{2}+\omega_{0}^{2}}{\omega_{1}^{2}+\omega_{0}^{2}}\right)}{4 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)} \text { and } \beta=\frac{\ln \left(10^{8}\right)}{2 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)}
$$

Finally, the function $f(j \omega)=\frac{\ln \left(\frac{\omega_{2}+j \omega}{\omega_{1}+j \omega}\right)}{\ln \left(10^{8}\right)}$ which is fitted with 15 real poles.
Note: $\omega_{0}=2 \pi f_{p}, \omega_{1}=10^{4}, \omega_{2}=10^{12}, \omega=2 \pi f$ and $f p$ the polarization frequency (FP parameter).

- Compat dispersive model (сомрАт=1)

$$
G=G_{o}+G_{d} \times \frac{f}{\sqrt{1+\left(\frac{f}{f_{g d}}\right)^{2}}}
$$

where $f_{g d}$ is a cut-off frequency; if $f_{g d}$ value is zero then G keeps linear dependency on the frequency. Default is zero.

The $R_{0}, G_{0}, R_{s}$ and $G_{d}$ matrices are optional (default value is zero). $L_{o}$ and $C_{o}$ matrices must be described in the RLGC file. Since these matrices are symmetrical, only the lower-triangular parts are specified in the RLGC file.

The diagonal terms of $L_{o}$ and $C_{o}$ matrices must be positive non-zero; the diagonal terms of $R_{0}$, $R_{s}, G_{o}$ and $G_{d}$ matrices must be non-negative. Off-diagonal terms of $C_{o}, G_{o}$ and $G_{d}$ are nonpositive.

## Comments

A comment line can be specified by an asterisk '*' at the beginning of the line. This comments out the entire line.

## Separator

The number can be separated by any combination of the characters shown in the table below:

## Table 4-11. RLGC Separator Characters

| Character |
| :--- |
| Space |
| Tab |
| New line |
| , |
| $;$ |
| $($ |
| ) |
| $[$ |
| ] |
| $\{$ |
| $\}$ |

## Example RLGC file

Filename: 2lin.rlc.

```
*RLGC matrices for 2 frequency-dependent lines
*N (number of lines)
*********************
2
* Lo
*******
0.3481e-6
0.5458e-7 0.3481e-6
* Co
*******
0.1593e-9
-0.2578e-10 0.1651e-9
* Ro
*******
75
0 50
* Go
*******
0.2421e-3
-0.4860e-4 0.2070e-3
* Rs
*******
0.0025
0.0.0014
```

```
* Gd
*******
1.2e-13
-4.1e-14 1.1e-13
```


## RLGC Model Syntax

The RLGC model is a model, which contains the values of $R, L, C, G, R_{s}$ and $G_{d}$ matrices per unit length. There is no limitation on the number of coupled lines. Since the matrices are symmetric, only the lower-triangular parts of the matrices have to be described in the RLGC model. Inductance and capacitance matrices $\left(\mathrm{C}_{\mathrm{o}}\right.$ and $\left.\mathrm{L}_{\mathrm{o}}\right)$ have to be specified, the other matrices can be optional.

## General Instantiation of the Model

```
.MODEL model_name W MODELTYPE=RLGC N=nb_line
+ Lo=Lo_matrix_entries Co=Co_matrix_entries
+ [Ro=Ro_matrix_entries] [Go=Go_matrix_entries]
+ [Rs=Rs_matrix_entries] [Gd=Gd_matrix_entries]
```


## Parameters

- $N=n b \_l i n e$

Number of lines.

- Lo=Lo_matrix_entries

Elements of the DC inductance matrix (per unit length).

- Co=Co_matrix_entries

Elements of the DC capacitance matrix (per unit length).

- Ro=Ro_matrix_entries

Elements of the DC resistance matrix (per unit length).

- Go=Go_matrix_entries

Elements of the DC conductance matrix (per unit length).

- Rs=Rs_matrix_entries

Elements of the skin-effect inductance matrix (per unit length):

$$
R=R_{o}+(1+i) \sqrt{f} R s
$$

- Gd=Gd_matrix_entries

Elements of the dielectric-loss conductance matrix (per unit length). The frequency dependent conductance uses the parameters Gs and $f p$ (polarization frequency: $\mathbf{F P}$ parameter). It can be modeled in two ways according to the multidebye parameter:

- One-pole debye model (multidebye=0)

$$
G=G_{o}+\frac{G_{d}}{2 \pi} \times \frac{i 2 \pi f \times 2 \pi f p}{i 2 \pi f+2 \pi f p}
$$

where $f p$ is the polarization frequency (FP parameter).

- Multi-pole debye model (multidebye=1)

By using this option, we build a complex frequency-dependent capacitance matrix:

$$
C(\omega)=C_{i n f}+f(j \omega) C_{d}
$$

Therefore, line conductance per unit length becomes:

$$
Y(j \omega)=G_{o}+(j \omega) C_{i n f}+(j \omega) f(j \omega) C_{d}
$$

where: $C_{\text {inf }}=C-\alpha G_{d}$ and $C_{d}=\beta G_{d} ; C$ and $G s$ are the user-defined matrices. with:

$$
\alpha=\frac{\ln \left(\frac{\omega_{2}^{2}+\omega_{0}^{2}}{\omega_{1}^{2}+\omega_{0}^{2}}\right)}{4 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)} \text { and } \beta=\frac{\ln \left(10^{8}\right)}{2 \pi\left(\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{1}}\right)-\operatorname{atan}\left(\frac{\omega_{0}}{\omega_{2}}\right)\right)}
$$

Finally, the function $f(j \omega)=\frac{\ln \left(\frac{\omega_{2}+j \omega}{\omega_{1}+j \omega}\right)}{\ln \left(10^{8}\right)}$ which is fitted with 15 real poles.
Note: $\omega_{0}=2 \pi f_{p}, \omega_{1}=10^{4}, \omega_{2}=10^{12}, \omega=2 \pi f$ and $f p$ the polarization frequency ( FP parameter).

- Compat dispersive model (COMPAt=1)

$$
G=G_{o}+G_{d} \times \frac{f}{\sqrt{1+\left(\frac{f}{f_{g d}}\right)^{2}}}
$$

where $f_{g d}$ is a cut-off frequency; if $f_{g d}$ value is zero then G keeps linear dependency on the frequency. Default is zero.

## Example RLGC Model

Circuit name: RLGCmodel_example.cir.

```
.MODEL model_rlgc W MODELTYPE=RLGC N=2
+ Lo = 0.3481e-6
+ 0.5458e-7 0.3481e-6
+ Co = 0.1593e-9
+ -0.2578e-10 0.1651e-9
```

```
+ Ro = 75
+ 0 50
+Go = 0.2421e-3
+ -0.4860e-4 0.2070e-3
+ Rs = 0.0025
+ 0.0014
+ Gd = 1.2e-13
+ -4.1e-14 1.1e-13
```


## Tabular RLGC Model Syntax

The Tabular model is an extension of the RLGC model, which allows to model transmission line arbitrary frequency-dependent behavior. There is no limitation on the number of coupled lines. Inductance and capacitance tabular matrices $\left(\mathrm{C}_{\mathrm{o}}\right.$ and $\left.\mathrm{L}_{\mathrm{o}}\right)$ have to be specified, the other tabular matrices are optional. Each tabular matrix is described in a .model statement.

## General Instantiation of the Model

```
.MODEL model_name sp W MODELTYPE=TABLE N=nb_line
+ LMODEL=L_freq_model CMODEL=C_freq_model
+ [RMODEL=R_freq_model] [GMODEL=G_freq_model] [FITTABLEMODEL=val]
```


## Parameters

- $N=n b \_l i n e$

Number of lines.

- LMODEL=L_freq_model

Name of the model containing the sampled values of the inductance matrix.

- CMODEL=C_freq_model

Name of the model containing the sampled values of the capacitance matrix.

- RMODEL=R_freq_model

Name of the model containing the sampled values of the resistance matrix. Default is zero.

- GMODEL=G_freq_model

Name of the model containing the sampled values of the conductance matrix. Default is zero.

- FITTABLEMODEL=val

When set to 1 , it will enable a causal model (admittance and propagation) to be built from non-causal tabulated data. If set to 0 (default), the tabulated data will not be modified to build the model and the built-in models are considered to be causals.

## Example Tablemodel

```
.model ex1 W MODELTYPE=TABLE N=2 LMODEL=lmod1
+ CMODEL=cmod1 Rmodel=rmod1 Gmodel=gmod1
```


## Sampled Matrix Model

This tabular matrix model gives a frequency-varying behavior of R, L, C and G matrices.

## General Instantiation of the Model

```
.MODEL model_name sp N=nb_line
+ SPACING=spacing_type VALTYPE=value_type
+ [INFINITY=matrix_values]
+ DATA=tabular_matrix_values
```


## Parameters

- model_name

Name of the model.

- N=nb_line

Number of lines.

- SPACING=spacing_type

Data spacing format: only NONUNIFORM type is handled.

- VALTYPE=value_type

Type of matrix elements: only REAL type is handled.

- INFINITY=matrix_values

Data points at infinity.

- DATA=tabuled_matrix_values

Specified frequency value and corresponding matrix data points. As the matrices are symmetric, only the lower-half portion is described. Syntax: DATA= (sampled_number, f1 data1 f2 data2 ...).

## Example Tablemodel

As the model is a "two coupled transmission line", the dimension of the matrices is 2 . Therefore, on each line of the DATA specification, after the sample number, the first value is the frequency, the second is the $(1,1)$ diagonal value, the third is the $(2,1)$ off-diagonal value, and the last is the $(2,2)$ diagonal value.

```
.model cmod1 sp N=2 SPACING=NONUNIFORM VALTYPE=REAL
+ DATA =(1,( 6.602360e-11 -7.04724e-12 6.602360e-11))
.MODEL lmod1 sp N=2 SPACING=NONUNIFORM VALTYPE=REAL
+ INFINITY=(4.0076e-7 4.6030e-8 4.0076e-7)
+ DATA=( 20,
+(0.000000e+00 3.934460e-07 4.6030e-08 3.933460e-07)
+(3.746488e+06 4.151139e-07 4.6030e-08 4.151959e-07)
+(7.726980e+06 4.084730e-07 4.6030e-08 4.085604e-07)
+(1.196411e+07 4.054831e-07 4.6030e-08 4.055730e-07)
+(1.648352e+07 4.037715e-07 4.6030e-08 4.037628e-07)
```

$+(3.204884 \mathrm{e}+074.008228 \mathrm{e}-074.6030 \mathrm{e}-084.008166 \mathrm{e}-07)$
$+(5.911330 e+073.988513 e-074.6030 e-083.988467 e-07)$
$+(7.650809 \mathrm{e}+073.981851 \mathrm{e}-074.6030 \mathrm{e}-083.981811 \mathrm{e}-07)$
$+(8.650875 e+073.978968 e-074.6030 e-083.978931 e-07)$
$+(9.756098 e+073.976313 e-074.6030 e-083.976278 e-07)$
$+(1.098398 e+083.973847 e-074.6030 e-083.973813 e-07)$
$+(1.235615 e+083.971538 e-074.6030 e-08 \quad 3.971507 e-07)$
$+(2.962963 e+083.958050 e-074.6030 e-083.958030 e-07)$
$+(3.428571 e+083.956319 e-074.6030 e-083.956300 e-07)$
$+(4.010283 e+083.954596 e-074.6030 e-083.954579 e-07)$
$+(5.753425 e+083.951106 e-074.6030 e-08 \quad 3.951092 e-07)$
$+(7.145791 e+083.949294 e-074.6030 e-083.949281 e-07)$
$+(9.230769 e+083.947392 e-074.6030 e-083.947380 e-07)$
$+(1.269625 e+093.945339 e-074.6030 e-083.945329 e-07)$
$+(4.000000 e+093.940153 e-074.6030 e-083.940147 e-07)$

+ )
.MODEL rmod1 sp N=2 SPACING=NONUNIFORM VALTYPE=REAL + DATA=( 18,
$+(0.000000 \mathrm{e}+008.765530 \mathrm{e}-016.299210 \mathrm{e}-038.765530 \mathrm{e}-01)$ $+(3.746488 e+066.028640 e+006.299210 e-036.028640 e+00)$ $+(7.726980 \mathrm{e}+068.270684 \mathrm{e}+006.299210 \mathrm{e}-038.270684 \mathrm{e}+00)$ $+(1.196411 \mathrm{e}+071.007694 \mathrm{e}+016.299210 \mathrm{e}-031.007694 \mathrm{e}+01)$ $+(2.131439 e+071.313620 e+016.299210 e-031.313620 e+01)$ $+(3.803487 e+071.727973 e+016.299210 e-031.727973 e+01)$ $+(6.741573 e+072.271433 e+016.299210 e-032.271433 e+01)$ $+(7.650809 \mathrm{e}+072.414031 \mathrm{e}+016.299210 \mathrm{e}-032.414031 \mathrm{e}+01)$ $+(9.756098 e+072.714662 e+016.299210 e-032.714662 e+01)$ $+(1.098398 e+082.845071 e+016.299210 e-032.845071 e+01)$ $+(1.764706 \mathrm{e}+083.620734 \mathrm{e}+016.299210 \mathrm{e}-03 \quad 3.620734 \mathrm{e}+01)$ $+(1.995249 e+083.844427 e+016.299210 e-033.844427 e+01)$ $+(2.264151 e+084.085570 e+016.299210 e-034.085570 e+01)$ $+(3.428571 e+085.012232 e+016.299210 e-035.012232 e+01)$ $+(4.010283 e+085.413628 e+016.299210 e-035.413628 e+01)$ $+(7.145791 e+087.197077 e+016.299210 e-03 \quad 7.197077 e+01)$ $+(1.269625 e+099.584070 e+016.299210 e-039.584070 e+01)$ $+(4.000000 \mathrm{e}+091.690795 \mathrm{e}+026.299210 \mathrm{e}-031.690795 \mathrm{e}+02)$ + )
.MODEL gmod1 sp $\mathrm{N}=2$ SPACING=NONUNIFORM VALTYPE=REAL + DATA=( 22,
$+(0.000000 \mathrm{e}+005.977166 \mathrm{e}-11 \quad 0.000000 \mathrm{e}+00 \quad 5.977166 \mathrm{e}-11)$
$+(3.746488 e+061.451137 e-05-1.821096 e-061.451043 e-05)$
$+(7.726980 e+062.992905 e-05-3.755938 e-062.992712 e-05)$
$+(1.196411 e+074.634076 e-05-5.815525 e-064.633777 e-05)$
$+(2.131439 \mathrm{e}+078.245729 \mathrm{e}-05-1.036052 \mathrm{e}-058.245196 \mathrm{e}-05)$
$+(3.803487 e+071.473209 \mathrm{e}-04-1.848803 \mathrm{e}-051.473114 \mathrm{e}-04)$
$+(5.911330 e+072.289642 e-04-2.873385 e-052.289494 e-04)$
$+(6.741573 e+072.611221 e-04-3.276951 e-05 \quad 2.611062 e-04)$
$+(7.650809 e+072.963396 e-04-3.718913 e-052.963205 e-04)$
$+(9.756098 e+073.778840 e-04-4.742254 e-053.778596 e-04)$
$+(1.098398 e+084.253437 e-04-5.339105 e-054.254163 e-04)$
$+(1.389961 e+085.383752 e-04-6.756338 e-05 \quad 5.383404 e-04)$
$+(1.564859 e+086.061286 e-04-7.606484 e-056.060795 e-04)$
$+(1.995249 e+087.728220 e-04-9.698528 e-057.727721 e-04)$
$+(2.264151 \mathrm{e}+088.769759 \mathrm{e}-04-1.100561 \mathrm{e}-048.769193 \mathrm{e}-04)$
$+(2.962963 e+081.146647 e-03-1.440240 e-041.147553 e-03)$
$+(3.428571 e+081.327992 e-03-1.666563 e-041.327906 e-03)$

```
+(4.757709e+08 1.842808e-03 -2.312632e-04 1.842689e-03)
+ (5.753425e+08 2.228580e-03 -2.796630e-04 2.228336e-03)
+(9.230769e+08 3.575363e-03 -4.486902e-04 3.575132e-03)
+ (1.959184e+09 7.588526e-03 -9.523220e-04 7.588036e-03)
+(4.000000e+09 1.549424e-02 -1.944324e-03 1.549234e-02)
+ )
```


## Error Message Treatment

Most of the errors you can meet with this model are the same as for the LDTL model, see "Error Message Treatment" on page 172.

Also, the following error message is displayed if there is a lack of value(s) in the C matrix description:

```
ERROR IN RLGC FILE 2lin.rlc : check matrix C
```


## Lossy Transmission Line: U Model

```
Uxx P1...PN PGNDin PN+1...P2N PGNDout UNAME L=length [SAVEFIT=val]
```

The U model is implemented in Eldo to simulate lossy-coupled uniform lines. This model can be used in all analysis modes (DC, AC, Transient, SST, SSTNOISE, or MODSST). Examples are provided in the directory $\$ M G C \_A M S \_H O M E /$ examples/tlines/U_model.

## Parameters

- $x x$

Transmission line name.

- P1...PN

The N nodes at one end of the line system for a system consisting of N lines.

- PGNDin

Reference node for the P1...PN nodes of the line system.

- $\mathrm{PN}+1 . . . \mathrm{P} 2 \mathrm{~N}$

The N nodes at the other end of the line system. The line number i in the line system connects the nodes Pi and $\mathrm{PN}+\mathrm{i}$.

- PGNDout

Reference node for the $\mathrm{PN}+1 \ldots \mathrm{P} 2 \mathrm{~N}$ nodes of the line system.

- UNAME

Name of the lossy transmission line model.

- L=length

Geometric length of the system (meter). Default value is 1.0. If $\mathrm{L}=0$, Eldo uses the default value.

- SAVEFIT=val

If the value is 1 , this option saves the initialization of the transmission line model (in the file circuit_name.fit), in order to speed up the following simulations of the same netlist. Default value is 0 .

## Example

Circuit name: Umodel_elev1_example.cir.

U1 1020 Umodel L=1.0e-3
Specifies a lossy transmission line U1 between nodes 1 and 2, the reference plane is the ground (node 0 ). The length of this transmission line is $1.0 \mathrm{e}-3$ and all the parameters are specified in the model called Umodel (.model u model).

## Model Syntax

```
.MODEL UNAME U LEVEL=3 ELEV=elev_val PLEV=plev_val
+ [DEV=dlev_val] [LLEV=llev_val] [Param=p_val]
```


## Parameters

- UNAME

Name of the model.

- LEVEL=3

Selects the model of lossy transmission line.

- ELEV=elev_val

Selects the specification format:
ELEV=1 $\rightarrow$ geometrical description.
ELEV $=2 \rightarrow$ precomputed model parameters (R, L, C, and G matrices).
ELEV $=3 \rightarrow$ measured parameters.

- PLEV=plev_val

Selects the type of transmission line: planar structure (plev=1), coax (plev=2) or twinhead ( $\mathrm{PLEv}=3$ ). Only planar structure is supported.

- DLEV=dlev_val

Specifies the dielectric and ground reference configuration. Two configurations are proposed: microstrip layered dielectric (DLEV=1) and stripline (DLEV=2). Default value is 1 .

- LLEV=llev_val

Reference plane inductance consideration (default is 0 ):
LLEV $=0 \rightarrow$ omit this inductance.
LLEV=1 $\rightarrow$ include this inductance (not supported).

- Param=p_val

Specifies parameters of the lines (depends on the specification format).

## Geometric Description: ELEV=1

## Restriction

Only single line can be described.

## Specific Parameters

## - DLEV

Type of Line;
DLEV=1 $\rightarrow$ Microstrip layered dielectric

DLEV=2 $\rightarrow$ Stripline

- NL

Number of line, default value is 1 . (only single line can be described).

- Ht

Conductor height, default value is $2.0 \mathrm{e}-4 \mathrm{~m}$.

- WD

Conductor width, default value is $3.0 \mathrm{e}-4 \mathrm{~m}$.

- TH

Conductor thickness, default value is $1.0 \mathrm{e}-4 \mathrm{~m}$.

- KD

Dielectric relative permittivity, default value is 10.0 .

- RHO

Conductor resistivity. Default value is $17 \mathrm{e}-9 \Omega \mathrm{~m}$ (copper).

## Example

Circuit name: Umodel_elev1_example.cir.

```
.MODEL Umodel U LEVEL=3 ELEV=1 PLEV=1 DLEV=2 NL=1
+ HT=1.0e-4 + WD=2.0e-4 TH=5.0e-5 RHO=1.785e-8
```

This model describes a lossy stripline.

## Precomputed Model Parameters: ELEV=2

The precomputed parameters correspond to the R, L, C and G matrices. Since these matrices are symmetric, only the upper-triangular parts are specified.

## Restriction

This description allows the specification of up to five signal conductors.

## Specific Parameters

- crj

Self capacitance per unit length $\left(\mathrm{Fm}^{-1}\right)$. Default value is $1.0 \mathrm{e}^{-9}$.

- cij

Mutual capacitance per unit length $\left(\mathrm{Fm}^{-1}\right)$. Default value is 0 .

- ljj

Self inductance per unit length $\left(\mathrm{Hm}^{-1}\right)$. Default value is $1.0 \mathrm{e}^{-6}$.

- lij

Mutual inductance per unit length $\left(\mathrm{Hm}^{-1}\right)$. Default value is 0 .

- rjj

Resistance per unit length $\left(\Omega \mathrm{m}^{-1}\right)$. Default value is 0 .

- grj

Self conductance per unit length $\left(\mathrm{Sm}^{-1}\right)$. Default value is 0 .

- gij

Mutual conductance per unit length $\left(\mathrm{Sm}^{-1}\right)$. Default value is 0 .

## Example

Circuit name: Umodel_elev2_example.cir.

```
.MODEL Umodel U LEVEL=3 ELEV=2 PLEV=1 r11=34.48
+ r22=34.48 + r33=34.48 l11=49.76n l22=49.76n l33=49.76n
+ l12=7.65n + l23=7.65n cr1=10.82p cr 2=11.24p cr 3=10.82p
+ c12=-1.97p + c23=-1.97p gr1=0.15u gr2=0.15u gr3=0.15u
```

This model describes three coupled lossy transmission lines.

## Measured Parameters: ELEV=3

This description corresponds to the electrical parameters.

## Restriction

Only single line can be described.

## Specific Parameters

- zK

Characteristic impedance $(\Omega)$.

- VREL

Relative velocity.

- DELAY

Delay(s) for length delen.

- CAPL

Linear capacitance in length clen. Default value is 1 .

- AT1

Attenuation factor in length atcen. Default value is 1 .

- DELEN

Unit of length (m) for delay. Default value is 1 .

- CLEN

Unit of length (m) for CAPd. Default value is 1 .

- AtLen

Unit of length for ati. Default value is 1 .

- FR1

Frequency at which dispersion starts (only affects resistance). If no value is specified, the dispersion will not be taken into account.

In order to discard redundant parameter sets, the following equations are used:
Table 4-12. Lossy Transmission Line: U Model Parameter Combinations

| Input Parameters | Computation |
| :--- | :--- |
| ZK, DELAY, DELEN, CAPL and <br> CLEN | Redundant, discard CAPL and CLEN |
| ZK, VREL, CAPL and CLEN | Redundant, discard CAPL and CLEN |
| ZK, DELAY and DLEN | $V R E L=\frac{D L E N}{D E L A Y \times C L I G H T}$ |
| ZK and VREL | $C=\frac{1.0}{Z K \times V R E L \times C L I G H T} \quad L=\frac{Z K}{V R E L \times C L I G H T}$ |
| ZK, CAPL and CLEN | $C=\frac{C A P L}{C L E N} \quad L=C \times Z K^{2}$ |
| CAPL, CLEN, DELAY and <br> DELEN | $C R E L=\frac{D E L E N}{D E L A Y \times C L I G H T}$ |
| CAPL, CLEN and VREL | $L=\frac{C A P L}{C L E N}$ |

## Example

Circuit name: Umodel_elev3_example.cir.

```
.MODEL Umodel U LEVEL=3 ELEV=3 PLEV=1 ZK=50 DELAY=10n AT1=1
```

This model describes a single lossy transmission line with a characteristic impedance of $50 \Omega$.

## Error Message Treatment

Most of the errors you can meet with this model are the same as for the LDTL model, see "Error Message Treatment" on page 172.

## Microstrip Models

A set of microstrip and stripline layout discontinuity structures is provided. This set is targeting RF simulations where a piece of microstrip or stripline discontinuity has to be included. They may also be used for integrated design of microstrip or stripline structures. The available set is as follows:

Microstrip Discontinuities:

- MTEE-Microstrip T Junction
- MBEND—Microstrip Bend (Arbitrary Angle, Optimally Mitered)
- MBEND2—90-degree Microstrip Bend (Mitered)
- MBEND3—90-degree Microstrip Bend (Optimally Mitered)
- MCORN—90-degree Microstrip Bend (Unmitered)
- MSTEP—Microstrip Step in Width
- VIA2-Cylindrical Via Hole in Microstrip

Stripline Discontinuities:

- SBEND—Unmitered Stripline Bend
- STEE—Stripline T Junction
- SSTEP—Stripline Step in Width


## MTEE—Microstrip T Junction

Figure 4-6. Microstrip T Junction


## Symbol

Figure 4-7. Microstrip T Junction Symbol

## Syntax

Yxx MTEE P1 P2 P3 P4 P5 P6 PARAM: [W1=val] [W2=val] [W3=val]

+ [T=val] [Er=val] [H=val]


## Parameters

Table 4-13. Microstrip T Junction Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| W1 | Conductor width of the first arm | $2.0 \mathrm{e}-3$ | meter |
| W2 | Conductor width of the second arm | $2.0 \mathrm{e}-3$ | meter |
| W3 | Conductor width of the third arm | $3.0 \mathrm{e}-3$ | meter |
| T | Conductor thickness | $5.0 \mathrm{e}-6$ | meter |
| ER | Dielectric relative permittivity | 4 | - |
| H | Dielectric thickness | $1.6 \mathrm{e}-3$ | meter |

## Model Validity Range

$$
\begin{gathered}
0.5 \leq \mathrm{W} 1 / \mathrm{H} \leq 2.0 \\
0.5 \leq \mathrm{W} 2 / \mathrm{H} \leq 2.0 \\
0.5 \leq \mathrm{W} 3 / \mathrm{H} \leq 2.0 \\
\text { Simulation Domains }
\end{gathered}
$$

DC, AC, TRANSIENT, and SST

## References

Brian C. Wadell, "Transmission Line Design Handbook", 1991 Artech House.

## Notes

The model is based on the microstrip line symmetric T junction equations given in the mentioned reference.

The model handles symmetrical T-junction only. If the specified W1 and W2 parameters are not identical, the geometrical mean of W1 and W2 parameters is computed and used.

$$
W 1=W 2=\sqrt{W 1 \cdot W 2} \text { for non-symmetrical T-junction }
$$

Figure 4-8 illustrates the model equivalent circuit and pins connections:
Figure 4-8. Equivalent circuit Microstrip T Junction


## Example

A simple MTEE s-parameter extraction example over a range of frequencies:

$$
\begin{array}{ll}
\text {. param w1 } & =2 \cdot 0 e-3 \\
\text { - param w2 } & =2 \cdot 0 e-3 \\
\text { - param w3 } & =3 \cdot 0 e-3 \\
\text { - param t } & =5 \cdot 0 e-6 \\
\text {. param Er } & =4
\end{array}
$$

```
.param h = 1.6e-3
.param frequency = 5e9
Ymtee MTEE t1a 0 t1b 0 t2 0 PARAM: W1=w1 W2=w2 w3=w3 T=t Er=Er + H=h
*** S-Parameters Extraction
V1a t1a 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
V1b t1b 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
V2 t2 0 IPORT=3 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param frequency le9 7e9 100e6
.sst fund1=frequency nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),frequency)
.extract fsst label=S12_Mag yval(SM(1,2),frequency)
.extract fsst label=S13_Mag yval(SM(1,3),frequency)
.extract fsst label=S21_Mag yval(SM (2,1),frequency)
.extract fsst label=S22_Mag yval(SM (2,2),frequency)
.extract fsst label=S23_Mag yval(SM (2,3),frequency)
.extract fsst label=S31_Mag yval(SM(3,1),frequency)
.extract fsst label=S32_Mag yval(SM(3,2),frequency)
.extract fsst label=S33_Mag yval(SM(3,3),frequency)
.end
```


## MBEND—Microstrip Bend (Arbitrary Angle, Optimally Mitered)

Figure 4-9. Microstrip Bend (Arbitrary Angle, Optimally Mitered)


## Symbol

Figure 4-10. Microstrip Bend (Arbitrary Angle, Optimally Mitered) Symbol

## Syntax

Yxx MBEND P1 P2 P3 P4 PARAM: [W=val] [H=val] [Er=val] [T=val]

+ [RHO=val] [TAND=val] [M=val] [ANGLE=val]


## Parameters

Table 4-14. Microstrip Bend (Arbitrary Angle, Optimally Mitered) Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| W | Conductor width | $2.0 \mathrm{e}-3$ | meter |
| H | Dielectric thickness | $1.6 \mathrm{e}-3$ | meter |
| ER | Dielectric relative permittivity | 4 | - |

Table 4-14. Microstrip Bend (Arbitrary Angle, Optimally Mitered) Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| T | Conductor thickness | $5.0 \mathrm{e}-6$ | meter |
| RHO | Conductor resistivity | $1.7 \mathrm{e}-8$ | Ohm.meter |
| TAND | Dielectric loss tangent | 0.0 | - |
| M | Optimal mitre percentage | 60 | $\%$ |
| ANGLE | Bend angle | 60 | degree |

## Model Validity Range

$1 \leq \mathrm{ER} \leq 128$
$0<$ ANGLE < 90
$0.01 \leq \mathrm{W} / \mathrm{H} \leq 100$

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

Brian C. Wadell, "Transmission Line Design Handbook", 1991 Artech House.

## Equations

$$
\begin{align*}
& M=\frac{100 X}{d} \\
& d-X=\sqrt{2} W\left(1-\frac{M}{100}\right)
\end{align*}
$$

The model is equivalent to a transmission line of length:

$$
l=\frac{2 M}{100 \sin (A N G L E)}
$$

Figure 4-11 illustrates the model equivalent circuit and pins connections:
Figure 4-11. Equivalent circuit Microstrip Bend (Arbitrary Angle, Optimally Mitered)


## Example

A simple MBEND s-parameter extraction example over a range of frequencies:

```
.param W = 2.0e-3
.param H = 1.6e-3
.param Er = 4
.param T = 5.0e-6
.param RHO = 1.7e-8
.param TAND = 0
.param M = 60
.param angle = 60
.param fx = 5e9
Ymbend MBEND in O out O PARAM: W=W H=H Er=Er T=T RHO=RHO
+ TAND=TAND M=M ANGLE=ANGLE
*** S-Parameters Extraction
Vin in 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
Vout out 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param fx le9 7e9 100e6
.sst fund1=fx nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),fx)
.extract fsst label=S12_Mag yval(SM(1,2),fx)
.end
```


## MBEND2—90-degree Microstrip Bend (Mitered)

Figure 4-12. 90-degree Microstrip Bend (Mitered)


## Symbol

Figure 4-13. 90-degree Microstrip Bend (Mitered) Symbol

```
Syntax
    Yxx MBEND2 P1 P2 P3 P4 PARAM: [H=val] [W=val] [Er=val]
```


## Parameters

Table 4-15. 90-degree Microstrip Bend (Mitered) Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| H | Substrate thickness | $1.6 \mathrm{e}-3$ | meter |
| W | Conductor width | $2.0 \mathrm{e}-3$ | meter |
| ER | Dielectric constant | 4 | - |

Model Validity Range
$0.2<\mathrm{W} / \mathrm{H}<6$
$2.36<$ ER < 10.4
Simulation frequency < 12/H (Frequency in GHz, H in mm)

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

M. Kirschning, R. H. Jansen, and N. H. L. Koster. "Measurement and Computer-Aided Modeling of Microstrip Discontinuities by an Improved Resonator Method," 1983 IEEE MTTS International Microwave Symposium Digest, May 1983, pp.495-497.

## Equations

The equivalent circuit of the MBEND2 consists of two inductors and a capacitor, shown in Figure 4-14.

Equations used to calculate the equivalent circuit component values:

$$
\begin{aligned}
& \frac{C}{H}=\frac{W}{H}\left[7.6 \mathrm{Er}+3.8+\frac{W}{H}(3.93 \mathrm{Er}+0.62)\right] \quad \frac{p F}{m} \\
& \frac{L}{H}=441.2712\left\{1-1.062 \exp \left[-0.177\left(\frac{W}{H}\right)^{0.947}\right]\right\} \quad \frac{p F}{m}
\end{aligned}
$$

## Notes

The model parameters validity ranges were tested at the corners and some typical design values.

## Figure 4-14. Equivalent circuit MBEND2



## Example

A simple MBEND2 s-parameter extraction example over a range of frequencies:

```
.param H = 1.6e-3
.param W = 2.0e-3
.param Er = 4
.param fx = 1e9
Ymbend2 MBEND2 in 0 out 0 PARAM: H=H W=W Er=Er
*** S-Parameters Extraction
```

```
Vin in 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
Vout out 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param fx 1e9 7e9 100e6
.sst fund1=fx nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),fx)
.extract fsst label=S12_Mag yval(SM(1,2),fx)
.end
```


## MBEND3—90-degree Microstrip Bend (Optimally Mitered)

Figure 4-15. 90-degree Microstrip Bend (Optimally Mitered)


## Symbol

Figure 4-16. 90-degree Microstrip Bend (Optimally Mitered) Symbol

## Syntax

Yxx MBEND3 P1 P2 P3 P4 PARAM: [W=val] [H=val] [Er=val] [T=val]

+ [RHO=val] [TAND=val]


## Parameters

Table 4-16. 90-degree Microstrip Bend (Optimally Mitered) Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| W | Conductor width | $2.0 \mathrm{e}-3$ | meter |
| H | Dielectric thickness | $1.6 \mathrm{e}-3$ | meter |
| ER | Dielectric relative permittivity | 4 | - |
| T | Conductor thickness | $5.0 \mathrm{e}-6$ | meter |
| RHO | Conductor resistivity | $1.7 \mathrm{e}-8$ | Ohm.meter |

Table 4-16. 90-degree Microstrip Bend (Optimally Mitered) Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| TAND | Dielectric loss tangent | 0.0 | - |

## Model Validity Range

$0.25 \leq \mathrm{W} / \mathrm{H} \leq 2.75$
$2.5 \leq \mathrm{ER} \leq 25$
Simulation frequency < $15 / \mathrm{h}$ (Frequency in GHz, H in mm)

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

Brian C. Wadell, "Transmission Line Design Handbook", 1991 Artech House.

## Equations

The optimal miter is given by:

$$
M=52+65 e^{-1.35\left(\frac{W}{H}\right)}=\frac{100 X}{d}
$$

and is modeled as a transmission line of length:

$$
L=W\left[1.04+1.3 e^{-1.35\left(\frac{W}{H}\right)}\right] \quad m
$$

The following figure illustrates the model equivalent circuit and pins connections:
Figure 4-17. Equivalent Circuit MBEND3


## Example

A simple MBEND3 s-parameter extraction example over a range of frequencies:

```
.param W = 2.0e-3
.param H = 1.6e-3
.param Er = 4
```

```
.param T = 5.0e-6
.param RHO = 1.7e-8
.param TAND = 0
.param fx = 5e9
Ymbend3 MBEND3 in O out O PARAM: W=W H=H Er=Er T=T RHO=RHO
+ TAND=TAND
*** S-Parameters Extraction
Vin in 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
Vout out 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param fx 1e9 7e9 100e6
.sst fund1=fx nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),fx)
.extract fsst label=S12_Mag yval(SM(1,2),fx)
.end
```


## MCORN—90-degree Microstrip Bend (Unmitered)

Figure 4-18. 90-degree Microstrip Bend (Unmitered)


## Symbol

Figure 4-19. 90-degree Microstrip Bend (Unmitered) Symbol


```
Syntax
    Yxx MCORN P1 P2 P3 P4 PARAM: [W=val] [H=val] [Er=val]
```


## Parameters

Table 4-17. 90-degree Microstrip Bend (Unmitered) Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| H | Substrate thickness | $1.6 \mathrm{e}-3$ | meter |
| W | Conductor width | $2.0 \mathrm{e}-3$ | meter |
| ER | Dielectric constant | 4 | - |

## Model Validity Range

$$
0.1 \leq \mathrm{W} / \mathrm{H} \leq 6
$$

$2 \leq \mathrm{ER} \leq 15$

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

M. Kirschning, R. H. Jansen, and N. H. L. Koster. "Measurement and Computer-Aided Modeling of Microstrip Discontinuities by an Improved Resonator Method," 1983 IEEE MTTS International Microwave Symposium Digest, May 1983, pp. 495-497.

## Equations

The equivalent circuit of a microstrip corner is a lumped network of two inductors and a capacitor, as shown in Figure 4-20.

Figure 4-20. Equivalent circuit Microstrip corner


The following equations are used to calculate the values of the model lumped components:

$$
\begin{aligned}
& \left.L=\left(1-1.35 \times e^{\left\{-0.18\left(\frac{W}{H}\right)^{1.39}\right.}\right\}\right) \times 0.2 \quad n H \\
& C=\left\{(10.35 \mathrm{Er}+0.25)\left(\frac{W}{H}\right)^{2}+(2.6 \mathrm{Er}+5.44)\left(\frac{W}{H}\right)\right\} 0.001 \times H \quad p F
\end{aligned}
$$

where H is in mm .

## Example

A simple MCORN s-parameter extraction example over a range of frequencies:

```
.param H = 1.6e-3
.param W = 2.0e-3
```

```
.param Er = 4
.param fx = 5e9
Ymcorn MCORN in O out O PARAM: H=H W=W Er=Er
*** S-Parameters Extraction
Vin in 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
Vout out 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param fx 1e9 7e9 100e6
.sst fund1=fx nharm1=1
.extract fsst label=S11_Mag_Eldo yval(SM(1,1),fx)
.extract fsst label=S12_Mag_Eldo yval(SM(1,2),fx)
.end
```


## MSTEP—Microstrip Step in Width

Figure 4-21. Microstrip Step in Width


Symmetrical Step


Asymmetrical Step

## Symbol

Figure 4-22. Microstrip Step in Width Symbol


## Syntax

```
Yxx MSTEP P1 P2 P3 P4 PARAM: [W1=val] [W2=val] [ER=val]
```

$+[\mathrm{H}=\mathrm{val}][\mathrm{F}=\mathrm{val}]$ [ASYMMETRICAL=val] [T=val]

## Parameters

Table 4-18. Microstrip Step in Width Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| W1 | Conductor width at port 1 | $2.0 \mathrm{e}-3$ | meter |
| W2 | Conductor width at port 2 | $0.5 \mathrm{e}-3$ | meter |
| H | Substrate thickness | $1.6 \mathrm{e}-3$ | meter |
| ER | Relative Dielectric constant | 4 | - |
| T | Conductor thickness | $5.0 \mathrm{e}-6$ | meter |
| ASYMMETRICAL | Selects between symmetrical and <br> asymmetrical step structures | 0 | - |
| F | Operating frequency | 1 e 9 | Hz |

1. ASYMMETRICAL only takes two values, 1 for asymmetrical, and 0 for symmetrical step.

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

Brian C. Wadell, "Transmission Line Design Handbook", 1991 Artech House.

## Equations

The equivalent circuit of a microstrip step is a lumped network of an inductor and a capacitor, as shown in Figure 4-23.

Figure 4-23. Equivalent circuit of a microstrip step in width


The model equations to calculate the lumped component values are given in the mentioned reference.

## Example

A simple MSTEP s-parameter extraction example over a range of frequencies:

```
.param W1 = 2.0e-3
.param W2 = 0.5e-3
.param H = 1.6e-3
.param ER = 4
.param Frequency = 1e9
.param T = 5.0e-6
Ymstep MSTEP t1a 0 t1b 0 PARAM: W1=W1 W2=W2 ER=ER H=H F=Frequency
ASYMMETRICAL=0 T=T
*** S-Parameters Extraction
V1a t1a 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
V1b t1b 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param Frequency 1e9 5e9 100e6
.sst fund1=Frequency nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),Frequency)
.extract fsst label=S12_Mag yval(SM(1,2),Frequency)
.end
```


## VIA2—Cylindrical Via Hole in Microstrip

Figure 4-24. Cylindrical Via Hole in Microstrip


Symbol
Figure 4-25. Cylindrical Via Hole in Microstrip Symbol

Syntax
Yxx VIA2 P1 P2 PARAM: [H=val] [R=val] [COND=val] [T=val] [F=val]

## Parameters

Table 4-19. Cylindrical Via Hole in Microstrip Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| H | Substrate thickness | $200.0 \mathrm{e}-6$ | meter |
| R | Via radius | $100.0 \mathrm{e}-6$ | meter |
| COND | Conductor conductivity | 58.842 e 6 | $1 /($ Ohm.meter) |
| T | Conductor thickness | $5.0 \mathrm{e}-6$ | meter |
| F | Operating center frequency | 1.0 e 9 | Hz |

## Model Validity Range

100um < H < 635um
$0.1<\mathrm{R} / \mathrm{H}<1.5$
$0<\mathrm{T}<\mathrm{R}$

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

M. Goldfarb and R. Pucel. "Modeling Via Hole Grounds in Microstrip," IEEE Microwave and Guided Wave Letters, Vol. 1, No. 6, June, pp.135-137.

## Notes

The VIA2 is modeled as a series resistor and inductor network. The resistor and inductor values are based on equations given in the mentioned reference.

Figure 4-26 illustrates the model equivalent circuit and pins connections:
Figure 4-26. Equivalent circuit Cylindrical Via Hole in Microstrip


## Example

A simple VIA2 s-parameter extraction example over a range of frequencies:

```
.param H = 200e-6
.param R = 100e-6
.param COND = 58.824e6
.param T = 5.0e-6
.param fx = 5e9
Yvia2 VIA2 in out PARAM: H=H R=R COND=COND T=T F=fx
*** S-Parameters Extraction
```

```
Vin in 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
Vout out 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param fx 1e9 7e9 100e6
.sst fund1=fx nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),fx)
.extract fsst label=S12_Mag yval(SM(1,2),fx)
.end
```


## SBEND—Unmitered Stripline Bend

Figure 4-27. Unmitered Stripline Bend


## Symbol

Figure 4-28. Unmitered Stripline Bend Symbol

```
Syntax
    Yxx SBEND P1 P2 P3 P4 PARAM: [W=val] [B=val] [ER=val] [T=val]
    + [ANGLE=val] [F=val]
```


## Parameters

Table 4-20. Unmitered Stripline Bend Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| W | Conductor width | $0.1 \mathrm{e}-3$ | meter |
| B | Ground plane spacing | $280 \mathrm{e}-6$ | meter |
| T | Conductor thickness | $17 \mathrm{e}-6$ | meter |
| ER | Relative dielectric constant | 4.2 | - |
| ANGLE | Bend angle | 60 | degree |

Table 4-20. Unmitered Stripline Bend Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| F | Simulation frequency | 2 e 9 | Hz |

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

Altschuler, H.M., and A.A. Oliner, "Discontinuities in the Center Conductor of Symmetric Strip Transmission Line," IRE Transactions on Microwave Theory and Techniques, Vol. MTT-8, May 1960, pp. 328-339 and "Addendum to 'Discontinuities in the Center Conductor of Symmetric Strip Transmission Line'," Vol. MTT-10, No. 2, March 1962, p. 143.
K.C. Gupta, "Computer-Aided Design of Microwave Circuits", 1981, ARTECH HOUSE, INC.

Arthur A. Oliner, "Equivalent Circuits for Discontinuities in balanced Strip Transmission Line", Microwave Theory and Techniques, IEEE Transactions on, Volume: 3 Issue: 2, Mar 1955.

## Notes

The equivalent circuit of an unmitered stripline bend is a lumped network of two inductors and a capacitor whose values are based on equations given in the mentioned references. The equivalent circuit is shown in Figure 4-29.

Figure 4-29. Equivalent circuit of an unmitered stripline bend


## Example

A simple SBEND s-parameter extraction example over a range of frequencies:

| . param W | $=0.1 \mathrm{e}-3$ |
| :---: | :---: |
| . param B | $=280 \mathrm{e}-6$ |
| . param ER | $=4.2$ |
| . param T | $=17 \mathrm{e}-$ |
| . param ANGLE | $=60$ |
| .param F | $=2 \mathrm{e} 9$ |

```
Ysbend SBEND in 0 out 0 PARAM: W=W B=B ER=ER T=T ANGLE=ANGLE F=F
*** S-Parameters Extraction
Vin in 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
Vout out 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param f 1e9 5e9 100e6
.sst fund1=f nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),f)
.extract fsst label=S12_Mag yval(SM(1,2),f)
.end
```


## STEE—Stripline T Junction

Figure 4-30. Stripline T Junction


## Symbol

Figure 4-31. Stripline T Junction Symbol

```
Syntax
Yxx STEE P1 P2 P3 P4 P4 P5 PARAM: [W1=val] [W2=val] [W3=val]
+ [B=val] [ER=val] [T=val] [F=val]
```


## Parameters

Table 4-21. Stripline T Junction Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| W1 | First arm conductor width | $0.1 \mathrm{e}-3$ | meter |
| W2 | Second arm conductor width | $0.1 \mathrm{e}-3$ | meter |
| W3 | Third arm conductor width | $0.2 \mathrm{e}-3$ | meter |
| B | Ground plane spacing | $280 \mathrm{e}-6$ | meter |
| T | Conductor thickness | $17 \mathrm{e}-6$ | meter |
| ER | Relative dielectric constant | 4.2 | - |
| F | Simulation frequency | 2 e 9 | Hz |

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

Altschuler, H.M., and A.A. Oliner, "Discontinuities in the Center Conductor of Symmetric Strip Transmission Line," IRE Transactions on Microwave Theory and Techniques, Vol. MTT-8, May 1960, pp. 328-339 and "Addendum to 'Discontinuities in the Center Conductor of Symmetric Strip Transmission Line'," Vol. MTT-10, No. 2, March 1962, p. 143.

K.C. Gupta, "Computer-Aided Design of Microwave Circuits", 1981, ARTECH HOUSE, INC.

Arthur A. Oliner, "Equivalent Circuits for Discontinuities in balanced Strip Transmission Line", Microwave Theory and Techniques, IEEE Transactions on, Volume: 3 Issue: 2, Mar 1955.

## Notes

The model is based on the microstrip line symmetric T junction equations given in the mentioned references.

The model handles symmetrical T-junction only. If the specified W1 and W2 parameters are not identical, the geometrical mean of W1 and W2 parameters is computed and used.

$$
W 1=W 2=\sqrt{W 1 \cdot W 2} \text { for non-symmetrical T-junction }
$$

## Example

A simple STEE s-parameter extraction example over a range of frequencies:

```
.param W1 = 0.1e-3
.param W2 = 0.1e-3
.param W3 = 0.2e-3
.param B = 280e-6
.param ER = 4.2
.param T = 17e-6
.param frequency = 2e9
Ystee STEE t1a 0 t1b 0 t2 0 PARAM: W1=W1 W2=W2 W3=W3 B=B ER=ER T=T
F=frequency
*** S-Parameters Extraction
V1a t1a 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
V1b t1b 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
V2 t2 0 IPORT=3 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param frequency 1e9 5e9 100e6
.sst fund1=frequency nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),frequency)
.extract fsst label=S12_Mag yval(SM(1,2),frequency)
.extract fsst label=S13_Mag yval(SM(1,3),frequency)
.extract fsst label=S33_Mag yval(SM(3,3),frequency)
. end
```


## SSTEP—Stripline Step in Width

Figure 4-32. Stripline Step in Width


## Symbol

Figure 4-33. Stripline Step in Width Symbol


Syntax
Yxx SSTEP P1 P2 P3 P4 PARAM: [W1=val] [W2=val] [B=val] [T=val]

+ [ER=val] [F=val]


## Parameters

Table 4-22. Stripline Step in Width Parameters

| Parameter | Definition | Default | Units |
| :--- | :--- | :--- | :--- |
| W1 | Conductor width at port 1 | $0.10 \mathrm{e}-3$ | meter |
| W2 | Conductor width at port 2 | $0.15 \mathrm{e}-3$ | meter |
| B | Ground plane spacing | $280 \mathrm{e}-6$ | meter |
| T | Conductor thickness | $17 \mathrm{e}-6$ | meter |
| ER | Relative dielectric constant | 4.2 | - |
| F | Simulation frequency | 1 e 9 | Hz |

## Simulation Domains

DC, AC, TRANSIENT, and SST

## References

Brian C. Wadell, "Transmission Line Design Handbook", 1991 Artech House.

## Notes

The SSTEP is modeled as a series inductor. The inductor value is based on equations given in the mentioned reference.

Figure 4-34 illustrates the model equivalent circuit and pins connections:
Figure 4-34. Equivalent circuit for a Stripline Step in Width
P2 $\qquad$ P4

## Example

A simple SSTEP s-parameter extraction example over a range of frequencies:

```
.param W1 = 0.10e-3
.param W2 = 0.15e-3
.param B = 280e-6
.param T = 17e-6
.param ER = 4.2
.param frequency = 1e9
Ysstep SSTEP t1a 0 t1b 0 PARAM: W1=W1 W2=W2 B=B T=T ER=ER F=frequency
*** S-Parameters Extraction
V1a t1a 0 IPORT=1 RPORT=50 FOUR fund1 PdBm (1) -100 -90
V1b t1b 0 IPORT=2 RPORT=50 FOUR fund1 PdBm (1) -100 -90
.step param frequency 1e9 5e9 100e6
.sst fundl=frequency nharm1=1
.extract fsst label=S11_Mag yval(SM(1,1),frequency)
.extract fsst label=S12_Mag yval(SM(1,2),frequency)
.end
```


## Junction Diode

```
Dxx NP NN [NM] MNAME [[AREA=]AREA_VAL] [PERI|PJ|PD=PERIVAL]
+ [PGATE=PGATE_VAL] [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [OFF=0|1]
+ [STATISTICAL=0|1] [NOISE=0|1] [NONOISE]
Dxx NP NN [NM] MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]
```


## Parameters

- xx

Junction diode name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- NM

Name of the m node. Any number of pins can be specified. However, only some proprietary models will make use of additional pins, if any.

- mNAME

Name of the model used, as described in a . MODEL command.

- AREA=AREA_VAL

Model area factor. Default value is 1 .

- PERI|PJ|PD=PERIVAL

Perimeter of the diode. Default value is 0. PERI, PJ, and pd keywords are all synonymous.

- PGATE=PGATE_VAL

Length of the diode gate-edge. Default value is 0 (used for JUNCAP model only).

- $\mathbf{T}=$ TVAL

Sets temperature for the individual diode. Default nominal temperature is $27^{\circ} \mathrm{C}$.

- $\mathbf{m}=\mathrm{VAL}$

Device multiplier, simulating the effect of multiple devices in parallel. All currents, capacitances and resistances are affected by m. Default value is 1 .
The device is first evaluated without the $\boldsymbol{m}$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values w and $\mathbf{L}$ are not affected. Models are chosen depending on input w and $\mathbf{L}$, if required. Options mind, MAXL, MINw, MAXw, and so on, do not apply either, since they check the input values of w and $\mathbf{L}$.

## Note

Using an M factor value less than 1 could lead to simulating devices that cannot be physically realized.

- $\mathbf{T}[$ EMP $]=\mathrm{VAL}$

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- DTEMP=VAL

Temperature difference between the device and the rest of the circuit, in degrees Celsius. Default value is 0.0.

## Note

TEMP and DTEMP are mutually exclusive. If both are specified, the last one is used.

- $\mathbf{O F F}=0 \mid 1$

When set to 1 , causes no initial operating point to be calculated for the device during DC analysis, i.e. the device is "off". When set to 0 , the option is ignored.

- StATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 . Cannot be specified after nonoise keyword parameter.

- nonoise

Specifies that no noise model will be used for this device when performing noise analysis. Therefore, the device presents no noise contribution to the noise analysis.

- noise=0|1

When set to 0 , is equivalent to specifying the nonoise flag. When set to 1 , specifies that a noise model will be used for this device when performing noise analysis. Therefore, the device presents noise contribution to the noise analysis. This has precedence over any nonoise specification on a .model card.

- $\quad$ FMIN=VAL

Lower limit of the noise frequency band.

- $\quad$ max $=$ VAL

Upper limit of the noise frequency band.

- $\mathbf{N B F}=\mathrm{VAL}$

Specifies the number of sinusoidal sources with appropriated amplitude and frequency and with randomly distributed phase from which the noise source is composed. Default value is 50. This parameter has no effect when FMIN is set to 0 .

$\square$Note
FMIN and FMAX define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIn, FMAX) does not correspond to the output noise frequency band in the case of filters or oscillators and mixers that exhibit frequency conversion. FMIN is also used to specify the algorithm used to generate the noise source generated by the diode. When fmin>0 the diode noise source is generated with sinusoids; when FMIN=0 it is generated with a continuous spectrum between FMIN and FMAX.

## Handling Floating Gates

When .option floatgatecheck is set, will enable Eldo to issue a warning when a floating gate is detected and resume the simulation. Eldo will not consider reverse-biased diodes as active elements when checking for floating gates. . Option floatgaterr can be set to enable Eldo to issue an error when a floating gate is detected and stop the simulation. In addition Eldo can force detected floating gates to 0 using . Option floatgateo, which can be useful to change the topology of a circuit to achieve better convergence.

For more information please refer to "FLOATGATECHECK" on page 977.

## Combining Identical Diodes

Multiple identical diodes connected in parallel are reduced into a single instance using the $\mathbf{m}$ parameter, for example:
d1 12 diode1
d2 12 diode1
d3 13 diode1
Here, diode instances $d 1$ and $d 2$ will be replaced by:
d1 12 diode1 $\mathbf{M}=2$
but d3 will remain as it is because it is connected to different nodes.

Note
It will only work when no parameters are given on the instance.

For more information see "Merging Devices in Parallel" on page 120.

## Noise in Diodes

Noise models are available for diodes, see Noise Equations for All Levels of the Eldo Device Equations Manual.

## Example

d1 12 diode1 $\mathbf{T}=50$
Specifies a diode d1 placed between nodes 1 and 2 of model name diode 1 , and at temperature of $50^{\circ} \mathrm{C}$.

## Diode Model Syntax

.MODEL MNAME D [PAR=VAL]

Eldo provides several predefined diode models. The level parameter is placed first in the parameter list and specifies the model to be used. The options are listed in the table below. Parameters specific to the selected model are then assigned values following the level parameter. Default diode level is 1 .

Table 4-23. Diode Models

| LEVEL Value | Model Name |
| :--- | :--- |
| 1 | Berkeley Level 1 (Eldo Level 1) |
| 2 | Modified Berkeley Level 1 (Eldo Level 2) |
| 3 | Fowler-Nordheim Model (Eldo Level 3) |
| 4 | STMicroelectronics LEVEL 1 |
| 5 | STMicroelectronics LEVEL 2 |
| 6 | STMicroelectronics LEVEL 3 |
| $8^{1}$ | JUNCAP (Eldo Level 8) (DIOLEV $\neq 9$ ) |
| $8^{2}$ | JUNCAP2 (Eldo Level 8, DIOLEV $=11$ ) |
| 9 | Philips Diode Level 500 (Eldo Level 9) |
| 21 | Diode Level 21 |

1. Diode LEVEL 8 has a selector (DIOLEV) which when set to DIOLEV=9, the JUNCAP1 model is used.
2. Diode LEVEL 8 has a selector (DIOLEV) which when set to DIOLEV=11, the JUNCAP2 model is used.

## Using -compat with Diodes

Using the -compat runtime flag or selecting .option compat has the following effect on Diode Level values.

Table 4-24. Diode Models with -compat

| Level | Model Name |
| :--- | :--- |
| 2 | Fowler-Nordheim (Eldo LEVEL 3) |
| 3 | Berkeley Level 1 (Eldo LEVEL 1), by default SCALEV is set to 3 |
| 4 | JUNCAP Diode Model (Eldo LEVEL 8), by default DIOLEV is set to 9 |

## Output Quantities

For a listing of generic output quantities for diode models see "Diode Plotting and Printing" on page 809. This lists the syntax used to plot or print the values of both extrinsic and intrinsic pins. The information is divided into subsections of output type and analysis type.

## Berkeley Level 1 (Eldo Level 1)

The DC characteristics of the diode are determined by the parameters is and $\mathbf{N}$. An ohmic resistance, Rs, is included. Charge storage effects are modeled by a transit time, $\mathbf{T r}$, and a nonlinear depletion layer capacitance which is determined by the parameters cло, vs and m. The temperature dependence of the saturation current is defined by the parameters $\mathbf{E G}$, the energy and $\mathbf{x т r}$, and the saturation current temperature exponent. Reverse breakdown is modeled by an exponential increase in the reverse diode current and is determined by the parameters bv and IBV (both of which are positive numbers).

For model parameters, please refer to the Berkeley Level 1 Model (Eldo Level 1)
Parameters of the Eldo Device Equations Manual.

## Modified Berkeley Level 1 (Eldo Level 2)

The Eldo Level 2 model is based on the Berkeley diode model. It includes modified calculations for the reverse breakdown effects, the recombination effect and for the temperature behavior.

For model parameters, please refer to the Modified Berkeley Level 1 Model (Eldo Level
2) Parameters of the Eldo Device Equations Manual.

## Fowler-Nordheim Model (Eldo Level 3)

Fowler-Nordheim diode models are formed as a metal-insulator-semiconductor device or as a semiconductor-insulator-semiconductor layer device. The insulator is sufficiently thin to permit the tunneling of carriers. This element models electrically-alterable memory cells, air-gap switches, and other insulation breakdown devices.

## Example

```
*DIODE model definition
.model dio d level=3
*main circuit
d1 2 10 dio
```

Specifies the diode d1 placed between the nodes 2 and 10 of model name dio. Default parameter values are used for this Fowler-Nordheim model.

```
*DIODE model definition
.model diode1 d rs=4.68 bv=6.10 cjo=346p
+ tt=50n m=0.33 vj=0.75 is=1e-11 n=1.27
+ ibv=20ma
*main circuit
dbridge 2 10 diode1
```

Specifies the diode dbridge placed between nodes 2 and 10. The electrical parameters are defined in the diode 1 model.

## Note

level is not defined and so the Berkeley Level 1 diode model is used (level=1).

## JUNCAP (Eldo Level 8)

The JUNCAP model is the replica of the bulk-source/drain parasitic diode model included in the common MOS structure. This model may be used to define the bulk diode as an external component or to define new elements such as the substrate diode with similar behaviors.

LEVEL 8 has a selector (DIOLEv) which when set to diolev=9 means the JUNCAP1 model is used.

For model parameters, please refer to the JUNCAP Model (Eldo Level 8) Parameters of the Eldo Device Equations Manual.

## JUNCAP2 (Eldo Level 8, DIOLEV=11)

The JUNCAP2 model (LEVEL=8, DIOLEV=11) is the evolution of the standard JUNCAP1 junction diode model (LEVEL=8, DIOLEV=9).

For model parameters, please refer to the JUNCAP2 Model (Eldo Level 8, DIOLEV=11) Parameters of the Eldo Device Equations Manual.

## Philips Diode Level 500 (Eldo Level 9)

The Philips Diode Level 500 model provides a detailed description of the diode currents in forward and reverse biased Si-diodes. It is meant to be used for DC, transient and AC analysis.

For model parameters, please refer to the Philips Diode Level 500 Model (Eldo Level 9) Parameters of the Eldo Device Equations Manual.

## Diode Level 21

Level 21 is a combination of the Level 9 current equations and Level 1 capacitance model with a mix in the temperature dependencies of both models.

[^3]
## BJT—Bipolar Junction Transistor

Qxx NC NB NE [NS] [TH] MNAME [[AREA=]AREA_VAL] [AREAB=AREA_VAL]

+ [AREAC=AREA_VAL] [T[EMP]=VAL] [DTEMP=VAL] [M=VAL] [OFF=0|1]
+ [STATISTICAL=0|1] [NOISE=0|1] [NONOISE]
Qxx NC NB NE [NS] MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]


## Parameters

- xx

Name of the bipolar junction transistor.

- NC

Name of the collector node.

- NB

Name of the base node.

- NE

Name of the emitter node.

- MNAME

Name of the model used, as described in a .model command.

- NS

Substrate node. Default value is ground. This node can be specified in the .model card as BULK=<node_name>.

- TH

Thermal node, available only for the HICUM model (level 9). Voltage in this node represents the temperature increase of the device due to self-heating.

- AREA=AREA_VAL

Relative device area. Default value is 1 .

- AREAB=AREA_VAL

Base relative device area. Default is area.

- AREAC=AREA_VAL

Collector relative device area. Default is area.

- $\boldsymbol{T}=\mathrm{VAL}$

Sets temperature for the individual BJT. Default value is the current simulation temperature.

- $\mathbf{T}[$ EMP $]=$ VAL

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- $\mathbf{D T E M P}=\mathrm{VAL}$

Temperature difference between the device and the rest of the circuit, in degrees Celsius. Default value is 0.0.

## Note

TEMP and DTEMP are mutually exclusive. If both are specified, the last one is used.

- $\mathbf{M}=\mathrm{VAL}$

Device multiplier, simulating the effect of multiple devices in parallel. All currents, capacitances and resistances are affected by m. Default value is 1 .

The device is first evaluated without the $m$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values w and L are not affected. Models are chosen depending on input w and $\mathbf{L}$, if required. Options mind, maxl, minw, maxw, and so on, do not apply either, since they check the input values of w and L .

Note
Using an M factor value less than 1 could lead to simulating devices that cannot be physically realized.

- $\quad \mathbf{O F F}=0 \mid 1$

When set to 1 , causes no initial operating point to be calculated for the device during DC analysis, i.e. the device is "off". When set to 0 , the option is ignored.

- StATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .

- nonoise

Specifies that no noise model will be used for this device when performing noise analysis. Therefore, the device presents no noise contribution to the noise analysis.

- noise=0|1

When set to 0 , is equivalent to specifying the nonoise flag. When set to 1 , specifies that a noise model will be used for this device when performing noise analysis. Therefore, the device presents noise contribution to the noise analysis. This has precedence over any nonoise specification on a .model card.

- FMIN=VAL

Lower limit of the noise frequency band.

- FMAX=VAL

Upper limit of the noise frequency band.

- $\mathbf{N B F}=\mathrm{VAL}$

Specifies the number of sinusoidal sources with appropriated amplitude and frequency and with randomly distributed phase from which the noise source is composed. Default value is 50. This parameter has no effect when FMIN is set to 0 .

## Note

fmin and fmax define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency band in the case of filters or oscillators and mixers that exhibit frequency conversion. FMIN is also used to specify the algorithm used to generate the noise source generated by the BJT. When Fmin>0 the BJT noise source is generated with sinusoids; when FMIN=0 it is generated with a continuous spectrum between fmin and fmax.

## Example

$$
\text { q1 } 123 \text { bipol1 } \mathbf{t}=50
$$

Specifies a bipolar junction transistor q1 connected to nodes 1, 2 and 3, of model type bipol1, at a temperature of $50^{\circ} \mathrm{C}$.

## Combining Identical BJTs

Multiple identical BJTs connected in parallel are reduced into a single instance using the m parameter, for example:

```
q1 1 2 3 bipol1
q2 1 2 3 bipol1
q3 1 2 4 bipol1
```

Here, q3 will remain as it is because the nodes are different, but BJT instances q1 and q2 will be replaced by:

```
q1 1 2 3 bipol1 M=2
```


## Note

This will also work even if the Area parameter is specified. If two BJTs are merged and in addition have the same connectivity, the models will also have the same AREA.

For more information see "Merging Devices in Parallel" on page 120.

## BJT Model Syntax

```
.MODEL MNAME NPN SUBS=VAL [PAR=VAL]
.MODEL MNAME PNP SUBS=VAL [PAR=VAL]
.MODEL MNAME LPNP SUBS=VAL [PAR=VAL]
```

Both NPN and PNP model types are to be used for vertical structures. This means that most of the current flows in a vertical direction. With regard to a silicon integrated transistor, this flow can also be parallel to the surface of the silicon. This type of BJT is also called a lateral transistor. It is possible in Eldo for a PNP BJT model to be declared as lateral by using the LPNP keyword in the .model command. The current flow can also be affected by the subs parameter as follows:

If subs $=-1$, BJT is lateral.
If subs $=1$, BJT is vertical.
The level parameter is used to determine which model is to be used, as shown by the table below:

Table 4-25. BJT Models

| Lever | Model Name |
| :--- | :--- |
| 1 | Modified Gummel-Poon Model (Eldo Level 1) <br> (Berkeley Standard Model) |
| 2 | STMicroelectronics LEVEL 1 |
| 3 | BNR-HICUM Model |
| 4 | Philips Mextram 503.2 Model (Eldo Level 4) |
| 5 | Improved Berkeley Model (Eldo Level 5) |
| 7 | ROCK-HICUM Model |
| 8 | VBIC v1.2 Model (Eldo Level 8) |
|  | (versIon=1.15) VBIC v1.1.5 Model (Eldo Level 8) |
| 9 | HICUM Model (Eldo Level 9) |
| 22 | Philips Mextram 504 Model (Eldo Level 22) |
| 23 | Philips Modella Model (Eldo Level 23) |
| 24 | HICUM Level0 Model (Eldo Level 24) |

## Using -compat with BJT Models

Using the -compat runtime flag or selecting . OPtion compat has the following effect on BJT Level values.

Table 4-26. BJT Models with -compat

| LEVEi | Model Name |
| :--- | :--- |
| 2 | Improved Berkeley Model (Eldo LEVEL 5) |
| 2 | STMicroelectronics LEVEL 1 (Eldo LEVEL 2) |
| 4 | VBIC v1.2 (Eldo LEVEL 8) |
|  | (VERSION=1.15) VBIC v1.1.5 (Eldo LEVEL 8) |
| 6 | Philips Mextram 503.2 Model (Eldo LEVEL 4) |
| 8 | HICUM Model (Eldo LEVEL 9) |

If -compat is set, NPN are vertical, PNP are lateral.

## Output Quantities

For a listing of generic output quantities for BJT models see "BJT Plotting and Printing" on page 806. This lists the syntax used to plot or print the values of both extrinsic and intrinsic pins. The information is divided into subsections of output type and analysis type.

## Noise in BJTs

Noise models are available for BJTs Level 1 and Level 5 only, see the Noise sections of the Eldo Device Equations Manual in BJT Level 1 and BJT Level 5 respectively. Other BJT models have their own separate noise models.

## Automatic Selection of BJT Model Via AREA Specifications

BJT model versions can be selected via .model command areamin and areamax parameters. Whenever Eldo finds a BJT device for which the model name has no .model command, it searches through all defined models for a model of the same root name and whose areamin/areamax range matches the specified device size.

The BJT model is selected if the instance parameter area is consistent with areamin/areamax of the .MODEL command.

The separator in the .MODEL command should be a "." or a "_" character. If these characters exist multiple times in the model name, the last one specified is used as the separator. Examples for <root>.<extension>:

```
Q1 vplus in out 0 QND_model area=10
.model QND_model_2 NPN AREAMIN=3 AREAMAX=20
```

Here, 〈root> = QND_model, separator $=$ _ , <extension> $=2$.

```
Q1 vplus in out 0 QND.model area=10
.model QND.model_3 NPN AREAMIN=3 AREAMAX=20
```

Here, $\left\langle\right.$ root> $=$ QND. model, separator $=_{\_}$, <extension> $=3$.

## Example

```
Q1 C B S QND AREA = 10
    .MODEL QND.1 NPN AREAMIN=0 AREAMAX=5
    .MODEL QND.2 NPN AREAMIN=0 AREAMAX=20
```

In this example, the model selected for Q1 will be QND. 2 .

## Modified Gummel-Poon Model (Eldo Level 1)

The bipolar junction transistor model in Eldo is an adaptation of the integral charge control model of Gummel and Poon. This modified Gummel-Poon model extends the original model to include several effects at high bias levels. The model automatically simplifies to the less complex Ebers-Moll model when using default values. Parameter names used in the modified Gummel-Poon model have been chosen to be more easily understood by the program user, and to better reflect both physical and circuit design thinking.

Please refer to the BJT Level 1 Equations of the Eldo Device Equations Manual. For model parameters, please refer to the Modified Gummel-Poon Model (Eldo Level 1) Parameters of the Eldo Device Equations Manual.

## Philips Mextram 503.2 Model (Eldo Level 4)

This is the implementation of the Philips Mextram Bipolar Model 503.2 in Eldo. The basis of this work is the unclassified report 006/94 published by Philips Nat.lab., June 1995. In this model, the current through the epilayer is an explicit and continuous function of the internal and external base-collector junction voltages. The model covers all possible modes of operation such as ohmic current flow, saturated current flow and base push out both in the forward and reverse mode of operation.

Please refer to the Mextram Equations of the Eldo Device Equations Manual. For model parameters, please refer to the Philips Mextram 503.2 Model (Eldo Level 4) Parameters of the Eldo Device Equations Manual.

## Improved Berkeley Model (Eldo Level 5)

The improved Berkeley model is based on the Level 1 model (Gummel Poon). It includes several additional effects such as:

- Variable RC resistance due to velocity saturation.
- Quasi-saturation model based on a publication from G.M. Kull et al.
- Additional temperature effects.
- Variable exponent for high current roll off.

Please refer to the BJT Level 5 Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the Improved Berkeley Model (Eldo Level 5)
Parameters of the Eldo Device Equations Manual.

## Example

```
*BJT model definition
.model qmod npn bf=160 rb=100 cjs=2p
+ tf=0.3n tr=6n cje=3p cjc=2p vaf=100
*main circuit
q23 10 24 13 qmod
```

Specifies the bipolar transistor q23, with the collector connected to node 10, base to node 24 and emitter to node 13. Electrical parameters are specified in the model qmod.

## VBIC v1.2 Model (Eldo Level 8)

The VBIC model is a Bipolar Junction Transistor (BJT) model. VBIC stands for Vertical Bipolar Intercompany Model. The VBIC model was developed as an industry-standard, public domain replacement for the SPICE Gummel-Poon (SGP) model. VBIC is designed to be as similar as possible to the SGP model, yet overcomes its major deficiencies. VBIC improvements on SGP:

- Improved Early effect modeling
- Quasi-saturation modeling
- Parasitic substrate transistor modeling
- Parasitic fixed (oxide) capacitance modeling
- Includes an avalanche multiplication model
- Improved temperature modeling
- Base current is decoupled from collector current
- Electro-thermal modeling.

Eldo recognizes two versions of the VBIC model. To select each model the version parameter must be used as shown below:

Table 4-27. VBIC Version Selection

| Parameter Value | VBIC Version |
| :--- | :--- |
| vERSION $=1.2$ | VBIC v1.2 (default) |
| VERSION $=1.15$ | VBIC v1.1.5 |

The different model parameters are described in Parameter List for v1.2 and Parameter List for v1.1.5.

## (i)

Please refer to the VBIC Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the VBIC v1.2 Model (Eldo Level 8) Parameters of the Eldo Device Equations Manual.

## VBIC v1.1.5 Model (Eldo Level 8)

$\qquad$
v1.1.5 of the VBIC model was formerly Level 21 in Eldo.

Eldo recognizes two versions of the VBIC model. To select each model the version parameter must be used as shown above. For information on Version 1.2 see "VBIC v1.2 Model (Eldo Level 8)" on page 238

Please refer to the VBIC Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the VBIC v1.1.5 Model (Eldo Level 8) Parameters of the Eldo Device Equations Manual.

## HICUM Model (Eldo Level 9)

HICUM is a semi-physical compact bipolar transistor model. Semi-physical means that for arbitrary transistor configurations, defined by emitter size as well as number and location of base, emitter and collector fingers (or contacts, respectively), a complete set of model parameters can be calculated from a single set of technology-specific electrical and technological data. For this, the value of each element in the equivalent circuit is related to a function describing the dependence on so-called specific electrical data (such as sheet resistances and capacitances per unit area or length), technological data (such as width and doping of the collector region underneath the emitter), physical data (like mobilities), transistor
dimensions (such as design rules), operating point and temperature. The availability of such a semi-physical compact model is an important precondition for circuit optimization with respect to, for example, maximum speed and low power consumption, as well as for including process variations in the design.

The name HICUM was derived from HIgh-CUrrent Model, indicating that HICUM was initially developed with special emphasis on modeling the operating region at high current densities, which is very important for certain high-speed applications. Later, formulas for the calculation of the base resistance were developed, which include three-dimensional effects occurring in short transistors with an emitter length approaching the emitter width.

When the model parameter VERSION is set to a value of 2.2, 2.21, 2.22 or 2.23 , some new equations are used. When set to 2.1 , the old equations are used.

Table 4-28. HICUM version selection

| Parameter Value | HICUM Version |
| :--- | :--- |
| VERSION $=2.23$ | HICUM 2.23 (Default) |
| VERSION $=2.22$ | HICUM 2.22 |
| VERSION $=2.21$ | HICUM 2.21 |
| VERSION $=2.2$ | HICUM 2.2 (equivalent to HICUM 2.20) |
| $V E R S I O N=2.1$ | HICUM 2.1 |

For HICUM v2.1, please refer to the HICUM v2.1 Equations of the Eldo Device Equations Manual. For HICUM v2.1 model parameters, please refer to the HICUM v2.1 Model (Eldo Level 9) Parameters of the Eldo Device Equations Manual.

For HICUM v2.2, please refer to the HICUM v2.2 Equations of the Eldo Device Equations Manual. For HICUM v2.2 model parameters, please refer to the HICUM v2.2 Model (Eldo Level 9) Parameters of the Eldo Device Equations Manual.

## Philips Mextram 504 Model (Eldo Level 22)

This is the implementation of the Philips Mextram Bipolar Model 504 in Eldo. The basis of this work is the unclassified report NL-UR 2000/811 published by Philips Nat.Lab. The Mextram 504 model is implemented in Eldo as LEVEL=22.

Mextram 504 has two main improvements with respect to Mextram 503. The description of the currents and changes is much smoother as a function of bias, and the parameter extraction has been improved.

Four versions, Mextram 504, Mextram 504.1, Mextram 504.6.1 and Mextram 504.7, are accessible through the model parameter VERSION. By default, Mextram 504.7
$($ VERSION=504.7) is selected.

Please refer to the Mextram 504 Equations of the Eldo Device Equations Manual. For model parameters, please refer to the Philips Mextram 504 Model (Eldo Level 22)
Parameters of the Eldo Device Equations Manual.

## Printing/Plotting States

If a state is to be monitored by the user, the user has to type in the netlist for a given transistor Q1 to monitor, for example In:

```
.PLOT DC S(Q1->In) for DC or
.PLOT AC S(Q1->In) for AC or
.PLOT TRAN S(Q1->In) for TRAN
```


## Philips Modella Model (Eldo Level 23)

The Modella (Model lateral) model (Eldo Level = 23) developed by Philips provides an accurate model dedicated to lateral PNP devices. This new model is based on a totally new approach, accounting for the complex bi-dimensional structure of lateral transistors. The Modella model allows the simulation of lateral devices using real physically based parameters, instead of using less accurate empirically-modified vertical models, such as Gummel-Poon.

In the design of bipolar analog integrated circuits, greater flexibility is often achieved when both NPN and PNP transistors are incorporated in the circuit design. Many present day bipolar production processes use the conventional lateral PNP as the standard PNP transistor structure. For accurate modeling of such a lateral PNP transistor it is important to take the complex twodimensional nature of the transistor into account. The physics based Modella model (Model lateral) does exactly this. Using a modeling approach whereby the main currents and charges are independently related to bias-dependent minority carrier concentrations. Current crowding effects, high injection effects, and a bias dependent output impedance are all taken into account.

Please refer to the Modella Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the Philips Modella Model (Eldo Level 23)
Parameters of the Eldo Device Equations Manual.

## Example of a Modella Model Card

```
.MODEL modella_model LPNP LEVEL=23
+ IS=1.8E-16 BF= 131.0 IBF= 2.6E-14 VLF= 0.54 IK=1.1E-04
+ XIFV=0.43 EAFL= 20.5 EAFV= 75.0 BR= 25.0 IBR= 1.2E-13
+ VLR= 0.48 XIRV= 0.43 EARL= 13.1 EARV= 104.0 XES= 2.7E-3
```

```
+ XHES= 0.70 XCS= 3.0 XHCS= 1.0 ISS= 4.0E-13 RCEX= 5.0
+ RCIN= 47.0 RBCC= 10.0 RBCV= 10.0 RBEC= 10.0 RBEV= 50.0
+ REEX= 27.0 REIN= 66.0 RSB= 1.E15 TLAT= 2.4E-9 TFVR= 3.0E-8
+ TFN= 2.0E-10 CJE= 6.1E-14 VDE= 0.52 PE= 0.3 TRVR= 1.0E-9
+ TRN= 3.0E-9 CJC= 3.9E-13 VDC= 0.57 PC= 0.36 CJS= 1.3E-12
+ VDS= 0.52 PS= 0.35 TREF= 25.00 DTA= 0.0 VGEB = 1.206
+ VGCB= 1.206 VGSB= 1.206 VGB= 1.206 VGE= 1.206 VGJE= 1.123
+ AE= 4.48 SPB= 2.853 SNB= 2.6 SNBN= 0.3 SPE= 0.73 SPC= 0.73
+ SX=1.0 KF= 1.0 AF= 1.0 EXPHI= 1
```


## DC Operating Point Output

The DC operating point output facility gives information on the state of a device at its operating point. The following table shows the DC operating points that are printed in the .chi file in an OP and AC analysis.

Please refer to the DC Operating Point Output of the Eldo Device Equations Manual.
To print or plot a state for Q1, a BJT transistor, the following syntax is required:

## - For DC

```
.PLOT DC S(Q1->GBE)
```

- For AC

```
.PLOT AC S(Q1->GBE)
```

- For Transient

```
.PLOT TRAN S(Q1->GBE)
```


## HICUM Level0 Model (Eldo Level 24)

The HICUM (HIgh CUrrent bipolar compact transistor Model) Level0 model for bipolar transistors is a simplified version of HICUM v2.x with less computational effort while keeping more accurate simulation results than with the well-known Spice-Gummel-Poon-Model. The latter is caused by the more accurate transit time and transfer current formulation. However HICUM v2.x is recommended for more accurate results in physical based device modeling of bipolar transistors.

The HICUM/Level0 model is implemented in Eldo as LEVEL=24. Four versions of the HICUM/Level0 model are available in Eldo: versions v1.0, v1.11, v1.12 and v1.2. The different versions are accessible through the Eldo version specification:

Table 4-29. HICUM/Level0 version selection

| Parameter Value | HICUM/Level0 Version |
| :--- | :--- |
| VERSION $=1.2$ | HICUM/Level0 1.2 (Default) |

Table 4-29. HICUM/Level0 version selection

| Parameter Value | HICUM/Level0 Version |
| :--- | :--- |
| VERSION $=1.12$ | HICUM/Level0 1.12 |
| VERSION $=1.11$ | HICUM/Level0 1.11 |
| VERSION $=1.0$ | HICUM/Level0 1.0 | For model parameters, please refer to the HICUM Level0 Model (Eldo Level 24) Parameters of the Eldo Device Equations Manual.

## JFET—Junction Field Effect Transistor

Jxx ND NG NS MNAME [ [AREA=]AREA_VAL] [L=VAL] [W=VAL]
$+[\mathbf{T}[\mathbf{E M P}]=\mathrm{VAL}][\mathrm{DTEMP}=\mathrm{VAL}][\mathbf{M}=\mathrm{VAL}] \quad[\mathbf{O F F}=0 \mid 1] \quad[\mathbf{S T A T I S T I C A L = 0 | 1 ]}$

+ [NONOISE] [NOISE=1]
Jxx ND NG NS MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]


## Parameters

- xx

JFET transistor name.

- ND

Name of the drain node.

- NG

Name of the gate node.

- NS

Name of the source node.

- MNAME

Name of the model used, as described in a .MODEL command.

## Optional Parameters

- AREA

Relative device area (optional). Default value is 1 .

- $\mathrm{L}=\mathrm{VAL}$

Channel length in meters.

- $\mathbf{w = V A L}$

Channel width in meters.

- $\mathbf{T}[$ EMP $]=$ VAL

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- DTEMP=VAL

Temperature difference between the device and the rest of the circuit, in degrees Celsius.
Default value is 0.0.

## Note

TEMP and DTEMP are mutually exclusive. If both are specified, the last one is used.

- $\mathbf{M}=\mathrm{VAL}$

Device multiplier, simulating the effect of multiple devices in parallel. All currents, capacitances and resistances are affected by m. Default value is 1 .

The device is first evaluated without the $m$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values w and L are not affected. Models are chosen depending on input w and $\mathbf{L}$, if required. Options mind, MAXL, MINw, MAXw, and so on, do not apply either, since they check the input values of w and L .

## Note

Using an $\mathbf{m}$ factor value less than 1 could lead to simulating devices that cannot be physically realized.

- $\quad \mathbf{O F F}=0 \mid 1$

When set to 1 , causes no initial operating point to be calculated for the device during DC analysis, i.e. the device is "off". When set to 0 , the option is ignored.

- STATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .

- NONOISE

Specifies that no noise model will be used for this device when performing noise analysis. Therefore, the device presents no noise contribution to the noise analysis.

- NOISE=1

Specifies that a noise model will be used for this device when performing noise analysis.
Therefore, the device presents noise contribution to the noise analysis. This has precedence over any nonoise specification on a .model card.

- $\quad$ FMIN=VAL

Lower limit of the noise frequency band.

- FMAX = VAL

Upper limit of the noise frequency band.

- $\mathbf{N B F}=\mathrm{VAL}$

Specifies the number of sinusoidal sources with appropriated amplitude and frequency and with randomly distributed phase from which the noise source is composed. Default value is 50. This parameter has no effect when FMIN is set to 0 .
Note
FMIN and FMAX define the frequency band of the noise sources. This frequency range
may sometimes not correspond to the noise frequency band at the output of the circuit.
For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency
band in the case of filters or oscillators and mixers that exhibit frequency conversion.

## Note

FMIN is also used to specify the algorithm used to generate the noise source generated by the JFET. When FMIn>0 the JFET noise source is generated with sinusoids; when FMIN=0 it is generated with a continuous spectrum between FMIN and FMAX.

## Noise in JFETs

Noise models are available for JFETs, see the Noise section in the JFET and MESFET Equations chapter of the Eldo Device Equations Manual.

## Example

$$
\text { j1 } 123 \text { fet2 } \mathbf{t}=50
$$

Specifies a junction field effect transistor $\mathbf{j} 1$ placed between nodes 1,2 and 3 of model type fet2, and at a temperature of $50^{\circ} \mathrm{C}$.

## JFET Model Syntax

```
.MODEL MNAME NJF [PAR=VAL]
.MODEL MNAME PJF [PAR=VAL]
```

The JFET model is derived from the FET model of Schichman \& Hodges. The DC characteristics are defined by the vто and beta parameters, which determine the variation of drain current with gate voltage, LAMBDA, which determines the output conductance, and is, the saturation current of the two gate junctions. The ohmic resistances, RD and RS are included. Charge Storage is modeled by non-linear depletion layer capacitances for both gate junctions. These capacitances vary with the $-1 / 2$ power of junction voltage and are defined by cGs, cGD and Pb. The following predefined JFET device models can be selected using the level parameter:

Table 4-30. JFET Models

| Level | Model Name |
| :--- | :--- |
| 1 | Schichman \& Hodges Model |
| 2 | Enhanced Schichman \& Hodges Model |
| 3 | Extended Schichman \& Hodges Model |

Please refer to the JFET and MESFET Equations of the Eldo Device Equations Manual. For model parameters, please refer to the JFET Model (Eldo Level 1, 2 and 3) Parameters of the Eldo Device Equations Manual.

## Example

```
*JFET model definition
.model je20 njf vto=-3.2 beta=0.98m
+ lambda=2.5m cgs=5p cgd=1.3p is=7p
...
*main circuit
j1 3 2 0 je20
```

Specifies the transistor j 1 with drain connected to node 3 , gate to node 2 and source to ground. The electrical parameters are specified in the model je20.

## Output Quantities

For a listing of generic output quantities for JFET models see "JFET Plotting and Printing" on page 808. This lists the syntax used to plot or print the values of both extrinsic and intrinsic pins. The information is divided into subsections of output type and analysis type.

## MESFET—Metal Semiconductor Field Effect Transistor

```
Jxx ND NG NS MNAME [AREA] [L=VAL] [W=VAL] [T[EMP]=VAL] [DTEMP=VAL]
+ [M=VAL] [OFF=0|1] [STATISTICAL=0|1] [NONOISE] [NOISE=1]
Jxx ND NG NS MNAME [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]
```

See "JFET—Junction Field Effect Transistor" on page 244 for more details and the . MODEL syntax.

The following predefined MESFET device models can be selected using the level parameter:
Table 4-31. MESFET Models

| LEVEL | Model Name |
| :--- | :--- |
| 6 | Curtice Model |
| 7 | Schichman \& Hodges Model |
| 8 | Statz Model |
| 9 | TriQuint Model |

Please refer to the JFET and MESFET Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the MESFET Model (Eldo Level 6, 7 and 8)
Parameters of the Eldo Device Equations Manual.
For model parameters, please refer to the MESFET Model (Eldo Level 9, Update 1, 2 and 3) Parameters of the Eldo Device Equations Manual.

## MOSFET

```
Mxx ND NG NS [NB] [{NN}] [MOD[EL]=]MNAME [[L=]VAL] [[W=]VAL]
+ [AD=VAL] [AS=VAL] [PD=VAL] [PS=VAL] [GEO=VAL] [NRD=VAL] [NRS=VAL]
+ [M=VAL] [RDC=VAL] [RSC=VAL] [T[EMP]=VAL] [DTEMP=VAL] [STATISTICAL=0|1]
+ [NONOISE] [NOISE=1]
Mxx ND NG NS [NB] [{NN}] [MOD [EL]=]MNAME [W=VAL] [L=VAL]
+ [FMIN=VAL] [FMAX=VAL] [NBF=VAL] [STATISTICAL=0|1]
```


## Parameters

- $x x$

MOS transistor name.

- ND

Name of the drain node.

- NG

Name of the gate node.

- NS

Name of the source node.

- NB

Name of the bulk node. If not specified, the user can specify the parameter BULK=node_name with the .mODEL command, Eldo will connect the bulk node to node_name. By default node_name is 0 .

- NN

Name of the n node. Any number of pins can be specified. However, only the BSIMSOI3 model and some other proprietary models will make use of additional pins, if any.

- [MOD [EL] $=]$ MNAME

Name of the model used, as described in a . MODEL command. Using the optional mOD [EL] keyword, allows the user to avoid any instantiation errors that may occur due to the MOS instantiation allowing the specification of more than four pins.

Eldo will assume that the model name is the string that precedes the first string that is followed by an " =" sign. If there is no such string, the model name is assumed to be the 5th string, for example. In the example below, E is assumed to be the model name.

M1 A B C D E F ...
In the example below, F is assumed to be the model name.
M1 A B C D E F <PNAME>=<value>
In the example below, G is the model name because the mOD keyword is present.
M1 A B C D E MOD=G ...

- $\quad \mathbf{L}=$ VAL

Channel length in meters. Default value is 100 m .

- $\mathbf{W}=$ VAL

Channel width in meters. Default value is 100 m .

- $A D=V A L$

Drain area in $\mathrm{m}^{2}$.

- $\boldsymbol{A S}=\mathrm{VAL}$

Source area in $\mathrm{m}^{2}$.

- $\quad P D=V A L$

Drain perimeter in meters.

- $\mathbf{P S}=\mathrm{VAL}$

Source perimeter in meters.

- GEO=VAL

Switch which determines the layout of the device:
GEO=0 (default value) indicates the drain and source of the device are not shared by the other devices
GEO=1 indicates the drain is shared with another device
GEO=2 indicates the source is shared with another device
GEO=3 indicates the source and drain are shared with another device

- $\quad$ NRD=VAL

Equivalent number of squares of the drain diffusion. NRD is multiplied with sheet resistance RSH to obtain parasitic series drain resistance of each transistor. RSH is specified in the .MODEL command.

- NRS=VAL

Equivalent number of squares of the source diffusion. NRS is multiplied with sheet resistance RSH to obtain the parasitic series source resistance of each transistor.

- $\mathbf{M}=$ VAL

This is the device "multiplier," simulating the effect of multiple devices in parallel. Effective width, overlap, junction capacitances, and junction currents are multiplied by $\mathbf{m}$. Parasitic resistance values are divided by m. Default value is 1 .
The device is first evaluated without the $m$ factor, and at the very end of the device computation, all scaling quantities are multiplied / divided by m. Input values wand L are not affected. Models are chosen depending on input $\mathbf{w}$ and $\mathbf{L}$, if required. Options minc, MAXL, MINW, MAXw, and so on, do not apply either, since they check the input values of w and $\mathbf{L}$.

## Note

Using an M factor value less than 1 could lead to simulating devices that cannot be physically realized.

- $\mathrm{RDC}=\mathrm{VAL}$

Additional drain resistance due to contact resistance.

- $\quad$ RSC=VAL

Additional source resistance due to contact resistance.

- $\mathbf{T}[$ EMP $]=$ VAL

Sets temperature for the individual device, in degrees Celsius. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- DTEMP=VAL

Temperature difference between the device and the rest of the circuit, in degrees Celsius.
Default value is 0.0.
Note
TEMP and DTEMP are mutually exclusive. If both are specified, the last one is used.

- StATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the device. 0 means the device will keep its nominal values. 1 means the device has statistical variation applied. The global default can be specified via option statistical. Default is 1 .

- nONOISE

Specifies that no noise model will be used for this device when performing noise analysis. Therefore, the device presents no noise contribution to the noise analysis.

- NOISE=1

Specifies that a noise model will be used for this device when performing noise analysis. Therefore, the device presents noise contribution to the noise analysis. This has precedence over any nonoise specification on a .model card.

- $\quad$ FMIN=VAL

Lower limit of the noise frequency band.

- $\operatorname{FMAX}=\mathrm{VAL}$

Upper limit of the noise frequency band.

- $\quad \mathbf{N B F}=\mathrm{VAL}$

Specifies the number of sinusoidal sources with appropriated amplitude and frequency and with randomly distributed phase from which the noise source is composed. Default value is 50. This parameter has no effect when FMIN is set to 0 .

Note
FMIN and FMAX define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency band in the case of filters or oscillators and mixers that exhibit frequency conversion.

Note
FMIN is also used to specify the algorithm used to generate the noise source generated by the MOSFET. When FMIn>0 the MOSFET noise source is generated with sinusoids; when $\operatorname{FMIN}=0$ it is generated with a continuous spectrum between FMIN and FMAX.


## Note

Default value for all optional parameters is zero unless otherwise stated. If $\mathbf{L}$ or $\mathbf{w}$ are not specified, via the device instantiation statement, then they will take the values of the DEFL and DEFW parameters in the .OPTION command, see "DEFL=VAL" on page 984. The MOS geometry parameters can be assigned directly or via ".PARAM" on page 778.

## Combining Identical MOSFETs

Multiple identical MOS instances connected in parallel are reduced into a single instance using the m parameter, for example:

```
M1 1 2 2 3 4 MOS1 w=10u l=3u
M2 1 1 2 3 4 MOS1 w=10u l=3u
M3 1 2 % 3 4 MOS2 w=10u l=3u
```

Here, M3 will remain because it has a different model name, but MOS instances M1 and M2 will be replaced by:
$\begin{array}{llllllll}\mathbf{M} & 1 & 2 & 3 & 4 & \text { MOS } 1 & \mathbf{w}=10 u \quad \mathbf{l}=3 \mathrm{u} \quad \mathbf{M}=2\end{array}$

For more information see "Merging Devices in Parallel" on page 120.

## MOSFET Models

```
.MODEL MNAME NMOS [PAR=VAL]
.MODEL MNAME PMOS [PAR=VAL]
```

- $\quad \mathrm{PAR}=\mathrm{VAL}$

Names and values of the model parameters.
The following predefined MOSFET device models can be selected using the level parameter. The names in parentheses are aliases.

Table 4-32. MOSFET Models

| LEVEL | Model Name | Type Capacitive | Charge |
| :---: | :---: | :---: | :---: |
| 1 (BERK1) | Berkeley LEVEL 1 Berkeley SPICE Models | Yes |  |
| 2 (BERK2) | Berkeley LEVEL 2 Berkeley SPICE Models | xQc $\geq 0.5$ | x2c<0.5 |
| 3 (BERK3) | Berkeley LEVEL 3 Berkeley SPICE Models | $\mathrm{x} \mathrm{C} \times \geq 0.5$ | x ¢ $<0.5$ |
| 4 (MERCK4) | Merckel Charge Control MERCKEL MOSFET Models |  | Yes |
| 5 (MERCK1) | Merckel Simplified MERCKEL MOSFET Models | Yes |  |
| 6 (MERCK2) | Merckel Submicron MERCKEL MOSFET Models | Yes |  |
| 7 (MERCK3) | Merckel 3 (MHS) MERCKEL MOSFET Models | Yes |  |
| 8 (BSIM1) | Berkeley SPICE BSIM1 Model (Eldo Level 8) |  | Yes |
| 9 | reserved |  |  |
| 10 | reserved |  |  |
| 11 (BSIM2) | Berkeley SPICE BSIM2 Model (Eldo Level 11) |  | Yes |
| 12 (ELDO2) | Modified Berkeley Level 2 (Eldo Level 12) | $\mathrm{xQc} \geq 0.5$ | xQc<0.5 |
| 13 (ELDO3) | Modified Berkeley Level 3 (Eldo Level 13) | $\mathrm{xQc} \geq 0.5$ | xQc<0.5 |
| 14 | reserved |  |  |
| 16 (ELDO6) | Modified Lattin-Jenkins-Grove Model (Eldo Level 16) | $\mathrm{xQc} \geq 0.5$ | $\mathrm{xQc}<0.5$ |
| 17 (ELDO7) | Enhanced Berkeley Level 2 Model (Eldo Level 17) | $\mathrm{x} 0 \mathrm{c} \geq 0.5$ | $\mathrm{x} 0 \mathrm{c}<0.5$ |
| 18 (STMOS1) | STMicroelectronics LEVEL 1 |  | Yes |
| 19 (STMOS3) | STMicroelectronics LEVEL 3 |  | Yes |
| 20 to 40 | User Defined Models |  |  |
| 41 (STPROM1) | STMicroelectronics PROM LEVEL1 |  | Yes |
| 42 (STPROM3) | STMicroelectronics PROM LEVEL 3 |  | Yes |
| 43 (STMOS4) | STMicroelectronics MOS LEVEL 4 |  | Yes |
| 44 (EKV) | EKV MOS Model (Eldo Level 44 or EKV) | xQc $\geq 0.5$ | xQc<0.5 |

Table 4-32. MOSFET Models

| LEVEL | Model Name | Type Capacitive | Charge |
| :---: | :---: | :---: | :---: |
| 47 (BSIM3) | Berkeley SPICE BSIM3v2 Model (Eldo Level 47) |  | Yes |
| 53 (BSIM3V3) | Berkeley SPICE BSIM3v3 Model (Eldo Level 53) BSIM3v3.0, BSIM3v3.1 \& BSIM3v3.2 |  | Yes |
| 54 (SSIM) | Motorola SSIM Model (Eldo Level 54 or SSIM) |  | Yes |
| 55 (BSIMSOI3) | Berkeley SPICE BSIMSOI3 v1.3 Model (Eldo Level 55) |  | Yes |
| 56 (BSIMSOI3) | Berkeley SPICE BSIMSOI3 v2.x and v3.x Model (Eldo Level 56) |  | Yes |
| 59 (MOSP9) | Philips MOS 9 Model (Eldo Level 59 or MOSP9) |  | Yes |
| 60 (BSIM4) | Berkeley SPICE BSIM4 Model (Eldo Level 60) BSIM4.0, BSIM4.1, BSIM4.2, BSIM4.3 \& BSIM4.4 |  | Yes |
| 61 (EKV3) | EKV3 MOS Model (Eldo Level 61 or EKV3) |  | Yes |
| 62 (TFT) | TFT Polysilicon Model (Eldo Level 62) v1.0 \& v2.0 |  | Yes |
| 63 (MOSP11) | Philips MOS Model 11 Level 1101 (Eldo Level 63) |  | Yes |
| 64 (TFT) | TFT Amorphous-Si Model (Eldo Level 64) |  | Yes |
| 65 (MOSP11) | Philips MOS Model 11 Level 1100 (Eldo Level 65) |  | Yes |
| 66 (HISIM) | HiSIM Model (Eldo Level 66) |  | Yes |
| 67 (SP) | SP Model (Eldo Level 67) |  | Yes |
| 69 (M1102) | Philips MOS Model 11 Level 1102 (Eldo Level 69) |  | Yes |
| 70 (PSP) | Philips PSP Model (Eldo Level 70) |  | Yes |
| 71 (MM20) | Philips MOS Model 20 Level 2002 (Eldo Level 71) |  | Yes |
| 72 (BSIMSOI4) | Berkeley SPICE BSIMSOI4.0 Model (Eldo Level 72) |  | Yes |
| 73 (HISIMLDO) | HiSIM-LDMOS Model (Eldo Level 73) |  | Yes |
| 74 | MOSVAR Model (Eldo Level 74) |  | Yes |
| 75 (PSP103) | PSP103 Model (Eldo Level 75) |  | Yes |
| 101 (HVMOS) | HVMOS Model (Eldo Level 101) |  | Yes |

## Using -compat with MOSFET

Using the -compat runtime flag or selecting .OPTION COMPAT has the following effect on MOSFET Level values.

Table 4-33. MOS Levels with -compat

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
| 2 | Eldo2 (Eldo LEVEL 12) |
| 3 | Eldo3 (Eldo LEVEL 13) |
| 6 | Modified Lattin-Jenkins Grove Model (Eldo LEVEL 16) |
| 8 | Enhanced Berkeley LEVEL 2 (Eldo LEVEL 17) |
| 13 | Berkeley BSIM1 (Eldo LEVEL 8) |
| 39 | Berkeley BSIM2 (Eldo LEVEL 11) |
| 49 | Berkeley BSIM3 v3.0 \& BSIM3 v3.1 (Eldo LEVEL 53) |
| 50 | Philips MOS Model 9 (Eldo LEVEL 59) |
| 54 | Berkeley BSIM4.0.0 (Eldo LEVEL 60) |
| 57 | Berkeley BSIMSOI3v2 PD (Eldo LEVEL 56, SOIMOD=1) |
| 59 | Berkeley BSIMSOI3v2 FD (Eldo LEVEL 56, SOIMOD=3) |
| 68 | HiSIM Model (Eldo LEVEL 66) |
| 70 | BSIMSOIv4 Model (Eldo LEVEL 72) |

## Computation of Effective Parasitic Areas and Perimeters

If using MOSFET without specifying parasitic areas and perimeters, please refer to "XA=VAL" on page 974 for more information about computation of effective parasitic areas and perimeters.

## User Defined Models

By specifying UDMP=1 on UDM models, Eldo will add the extrinsic contribution to the intrinsic part defined by the user. The parasitic effects are computed according to the Berkeley Level 1 common approach.
.model M NMOS level=21 UDMP=1

## Output Quantities

For a listing of generic output quantities for MOSFET models see "MOSFET Plotting and Printing" on page 802. This lists the syntax used to plot or print the values of both extrinsic and intrinsic pins. The information is divided into subsections of output type and analysis type.

## Noise in MOSFETs

Noise models are available for MOSFETs, see Noise Models in MOSFETs of the Eldo Device Equations Manual.

In Eldo, MOS noise models are selected using either the device model parameters thmiev and flklev, or the global Eldo options thermal_noise=VAl and Flicker_noise=VAl.

Table 4-34. MOS Noise Models

| THERMAL_NOISE/THMLEV <br> Value | Noise Model |
| :--- | :--- |
| 0 | SPICE noise model-default ${ }^{1}$ |
| 1 | Strong inversion model |
| 2 | Weak and strong inversion model |
| 3 | Previous model with short channel effects |
| 4 | Strong inversion model with short channel effects |

1. Please note that the conductance used in the SPICE thermal noise equation is $\boldsymbol{g m}$. However, Eldo uses a more sophisticated computation of the total transistor conductance. This is given by the following equation:

$$
g t o t=g m+g d s+g m b
$$

Table 4-35. MOS Noise Models

| FLICKER_NOISE/FLKLEV <br> Value | Noise Model |
| :--- | :--- |
| 0 | SPICE noise model-default |
| 1 | Improved SPICE noise model |
| 2 | Improved SPICE noise model |
| 3 | Improved SPICE noise model |

## Selection of MOSFET Models via W/L Specifications (Binning)

$\qquad$
Note
This functionality used to be set with option modwl but has been the default since Eldo v5.1. Use option nomodwl to switch off the functionality.

By default, MOS model versions are selected via .model command wand a parameters (binning parameters). Whenever Eldo finds a MOS device for which the model name has no .MODEL command, it searches through all defined models for a model of the same root name and whose $\mathbf{w} / \mathbf{L}$ range matches the specified device size. For example, in the case below, Eldo will assign the model modroot. 2 to the MOSFET m1:

M1 $1 \begin{array}{lllllll}1 & 2 & 3 & 4 & \text { MODROOT } & \mathbf{w}=2 u \quad \mathbf{l}=3 u\end{array}$
. MODEL MODROOT. 1 NMOS VTO=1 WMIN=3u WMAX=5u LMIN=1u LMAX=5u
. MODEL MODROOT. 2 NMOS VTO=2 WMIN=1u WMAX=5u LMIN=1u LMAX=5u

## Note



Eldo selects the model to be assigned to MOS devices according to the geometric size of each device, even if these geometric sizes are modified at run-time via . Step commands.

The separator in the .MODEL command should be a "." or a "." character. If there are multiple occurrences of these characters in the model name, the last one specified is used as the separator. Specify option моDwLDот to only allow "." as the separator. When set, the character "_" can be used in the <root>. Examples for <root><separator><extension>:

Q1 vplus in out 0 QND_model area=10
.model QND_model_2 NPN AREAMIN=3 AREAMAX=20
Here, <root> = QND_model, separator = _, <extension> = 2 .
Q1 vplus in out 0 QND.model area=10
.model QND.model_3 NPN AREAMIN=3 AREAMAX=20
Here, <root> = QND.model, separator = _, <extension> = 3.
The binning models algorithm works in the following way:

1. A model with dimensions $\mathrm{W}, \mathrm{L}$ is chosen if the following formulae are satisfied:

$$
\begin{gathered}
V M I N+X W R E F \times S C A L M \leq \frac{W}{N F} \times S C A L E+X W \times S C A L M<W M A X+X W R E F \times S C A L N \\
V M I N+X L R E F \times S C A L M \leq L F \times S C A L E+X L \times S C A L M<L M A X+X L R E F \times S C A L N
\end{gathered}
$$

Where $\boldsymbol{X W R E F}, \boldsymbol{X W}, \boldsymbol{X L R E F}, \boldsymbol{X L}, \boldsymbol{S C A L M}$ are model parameters, $\boldsymbol{S C A L E}$ is a global parameter set with . OPtion SCALE=val, and $\boldsymbol{N F}$ (number of fingers) is a MOS instance parameter found in BSIM4 and other recent models.
$X L$ and $\boldsymbol{X W}$ default to 0.0. If $\boldsymbol{X L R E F}$ is not specified, $\boldsymbol{X L R E F}$ is set to $\boldsymbol{X L}$. If $\boldsymbol{X W R E F}$ is not specified, XWREF is set to $\boldsymbol{X W}$. SCALM and SCALE default to 1.
2. If when applying this rule, no match is found, Eldo will repeat the search with two inclusive inequalities:

$$
V M I N+X W R E F \times S C A L M \leq \frac{W}{N F} \times S C A L E+X W \times S C A L M \leq W M A X+X W R E F \times S C A L N
$$

$$
M I N+X L R E F \times S C A L M \leq L F \times S C A L E+X L \times S C A L M \leq L M A X+X L R E F \times S C A L M
$$

3. If a match is still not found, Eldo will issue an error.

Please also refer to "MODWLDOT" on page 988 and "NOMODWL" on page 989.

## BSIM4 Model Selection

The BSIM4 model has unique conditions for W/L specification model selection. The conditions for this model are shown below:

$$
W M I N \leq W / N F<W M A X \text { and } L M I N \leq L<L M A X
$$

Where $\boldsymbol{N F}$ is a parameter specified in the model instantiation card which defines the number of device fingers. An example is shown below:

```
.model nmos.1 nmos level=60 lmin=0.8u lmax=1.2u wmin=8u wmax=12u
.model nmos.2 nmos level=60 lmin=0.8u lmax=1.2u wmin=80u wmax=120u
m1 1 2 0 0 nmos w=10u nf=1 l=1u
m2 1 2 0 0 nmos w=100u nf=10 l=1u
```

In this case m 1 and m 2 will both use the nmos. 1 model.

## MOS Parasitics Common Approach

The need arises to unify the handling of the parasitic elements for all Eldo models, which are under our management. That is to say, that proprietary models are not concerned by those changes. To summarize, Eldo Levels 1, 2, 3, 8 (BSIM1), 11 (BSIM2), 12, 13, 16, 17, 44 (EKV), 47 (BSIM3v2), 53 (BSIM3v3) and 59 (MOSP9) are relevant to this feature. This parasitics common approach deals with the following effects:

- Parasitics access resistance calculation.
- Drain, source area and perimeter calculations.
- Bulk diode current calculations.
- Bulk diode capacitance calculations.


## Note



Noise calculations and geometric range definitions are also common.

Please refer to the Common Equations of the Eldo Device Equations Manual.

Four independent selectors alev, rlev, caplev and dcaplev ensure the switching between the different sets of equations. To ensure compatibility with previous versions of the software, an additional parameter arlev is necessary. arlev has priority over alev and rlev, so if arlev is specified: ALEV=RLEV=ARLEV.

Table 4-36. MOSFET Common Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 1 | ACM | Flag to control which parasitic models are to be used | 0 |  |
| 2 | OPTACM $^{1}$ | Flag to enable ACM control over parasitic models | 0 |  |
| 3 | CALCACM $^{2}$ | Flag to control the area and perimeter calculations when <br> ACM=12 | 0 |  |
| Parasitic Resistance Related Parameters | Switch selector | $*$ |  |  |
| 4 | RLEV | Drain ohmic resistance | 0 | $\Omega$ |
| 5 | RD | Source ohmic resistance | 0 | $\Omega$ |
| 6 | RS | Drain and Source diffusion sheet resistance | 0 | $\Omega / \mathrm{sq}$ |
| 7 | RSH | Additional drain resistance due to contact resistance | 0 | $\Omega$ |
| 8 | RDC | Additional source resistance due to contact resistance | 0 | $\Omega$ |
| 9 | RSC | Lateral diffusion into channel from source and drain <br> diffusion | $0^{*}$ | m |
| 10 | LD | Length of lightly doped diffusion adjacent to gate | 0 | m |
| 11 | LDIF | Length of heavily doped diffusion from contact to <br> lightly doped region | 0 | m |
| 12 | HDIF |  |  |  |

Table 4-36. MOSFET Common Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 13 | LGCD | Gate to contact length of drain side | 0 | m |
| 14 | LGCS | Gate to contact length of source side | 0 | m |
| 15 | SC | Spacing between contacts | -1 e 20 | m |
| 16 | RDD | Scalable drain resistance | 0 | $\Omega \mathrm{~m}$ |
| 17 | RSS | Scalable source resistance | 0 | $\Omega \mathrm{~m}$ |
| Area and Perimeter Related Parameters | Switch selector | $*$ |  |  |
| 18 | ALEV | Length account for masking and etching effects | 0 |  |
| 19 | DL | Width account for masking and etching effects | 0 | m |
| 20 | DW ${ }^{3}$ | Length diffusion layer shrink reduction factor | 1 |  |
| 21 | LMLT | Width diffusion layer shrink reduction factor | 1 |  |
| 22 | WMLT | Lateral diffusion into channel from bulk along width | 0 |  |
| 23 | WD | Bulk | Diode Current | Related Parameters |

Table 4-36. MOSFET Common Parameters

| Nr. | Name | Description | Default | Units |
| :---: | :---: | :---: | :---: | :---: |
| 36 | JSDSR | Sidewall saturation-current density due to diffusion from back contact | $1 \times 10^{-3}$ | $\mathrm{Am}^{-1}$ |
| 37 | JSGGR | Gate-edge saturation-current density due to electronhole generation at $V=V_{R}$ | $1 \times 10^{-3}$ | $\mathrm{Am}^{-1}$ |
| 38 | JSDGR | Gate-edge saturation-current density due to diffusion from back contact | $1 \times 10^{-3}$ | $\mathrm{Am}^{-1}$ |
| 39 | NBJ | Emission coefficient of the bottom forward current | 1 |  |
| 40 | NSJ | Emission coefficient of the sidewall forward current | 1 |  |
| 41 | NGJ | Emission coefficient of the gate-edge forward current | 1 |  |
| 42 | CJBR | Bottom junction capacitance at $V=V_{R}$ | $1 \times 10^{-12}$ | $\mathrm{Fm}^{-2}$ |
| 43 | CJSR | Sidewall junction capacitance at $V=V_{R}$ | $1 \times 10^{-12}$ | $\mathrm{Fm}^{-1}$ |
| 44 | CJGR | Gate-edge junction capacitance at $V=V_{R}$ | $1 \times 10^{-12}$ | $\mathrm{Fm}^{-1}$ |
| 45 | VDBR | Diffusion voltage of the bottom junction at $T=$ Tnom | 1 | V |
| 46 | VDSR | Diffusion voltage of the sidewall junction at $T=$ Tnom | 1 | V |
| 47 | VDGR | Diffusion voltage of the gate-edge junction at $T=$ Tnom | 1 | V |
| 48 | PB | Bottom-junction grading coefficient | 0.4 |  |
| 49 | PS | Sidewall junction grading coefficient | 0.4 |  |
| 50 | PG | Gate-edge-junction grading coefficient | 0.4 |  |
| 51 | TRDIO9 | Nominal temperature for Juncap junction diode model | TNOM (TR) | ${ }^{\circ} \mathrm{C}$ |
| Bulk Diode Capacitance Related Parameters (DIOLEV $\neq 9$ ) |  |  |  |  |
| 52 | DCAPLEV | Switch selector | * |  |
| 53 | CBD | Zero bias Bulk-Drain capacitance | 0 | F |
| 54 | CBS | Zero bias Bulk-Source capacitance | 0 | F |
| 55 | CJ | Zero bias bottom Bulk junction capacitance | 0* | $\mathrm{Fm}^{-2}$ |
| 56 | CJGATE | Zero bias gate-edge sidewall Bulk junction capacitance (only used when ALEV=3 and DCAPLEV=0) | 0 | $\mathrm{Fm}^{-1}$ |
| 57 | CJSW | Zero bias sidewall Bulk junction capacitance | 0 | $\mathrm{Fm}^{-1}$ |
| 58 | FC | Bulk junction forward bias capacitance coefficient | 0.5* |  |
| 59 | MJ | Bulk junction bottom grading coefficient | 0.5 |  |
| 60 | MJSW | Bulk junction sidewall grading coefficient | 0.33 |  |
| 61 | PB | Bulk bottom junction potential | 0.8* | V |

Table 4-36. MOSFET Common Parameters

| Nr. | Name | Description | Default | Units |
| :---: | :---: | :---: | :---: | :---: |
| 62 | PBSW | Bulk sidewall junction potential | PB | V |
| 63 | TT | Transit time | 0 | S |
| Temperature Effect Related Model Parameters |  |  |  |  |
| 64 | TNOM (TR) | Nominal temperature (TR for MOSP9 only) | 27 | ${ }^{\circ} \mathrm{C}$ |
| 65 | TMOD | Model temperature | TNOM | ${ }^{\circ} \mathrm{C}$ |
| 66 | TLEV | Temperature equation level selector | 0 |  |
| 67 | TLEVC | Temperature equation level selector for capacitances and potentials | 0 |  |
| 68 | CTA (TCJ) | Junction capacitance CJ temperature coefficient | 0 | ${ }^{\circ} \mathrm{K}^{-1}$ |
| 69 | CTP (TCJSW) | Junction sidewall capacitance CJSW temperature coefficient | 0 | ${ }^{\circ} \mathrm{K}^{-1}$ |
| 70 | PTA (TPB) | Junction potential PB temperature coefficient | 0 | $\mathrm{V}^{\circ} \mathrm{K}^{-1}$ |
| 71 | PTP (TPBSW) | Junction potential PHB temperature coefficient | 0 | $\mathrm{V}^{\circ} \mathrm{K}^{-1}$ |
| 72 | EG | Energy gap for PN junction diode | $1.11{ }^{4}$ | eV |
| 73 | GAP1 | First bandgap correction factor | $7.02 \times 10^{-4}$ | $\mathrm{eV}^{\circ} \mathrm{K}^{-1}$ |
| 74 | GAP2 | Second bandgap correction factor | 1108 | ${ }^{\circ} \mathrm{K}$ |
| 75 | TLEVI (LIS) | Saturation current temperature selector | 1 |  |
| 76 | ISTMP | Number of degrees that doubles IS value | 10 | ${ }^{\circ} \mathrm{C}$ |
| 77 | XTI | Saturation current temperature exponent | 0 |  |
| 78 | TLEVR | Access resistances temperature selector | 1 |  |
| 79 | TRD1 <br> (TC1,TRD) | Temperature coefficient (linear) for RD | 0 | ${ }^{\circ} \mathrm{K}^{-1}$ |
| 80 | TRD2 (TC2) | Temperature coefficient (quadratic) for RD | 0 | ${ }^{\circ} \mathrm{K}^{-2}$ |
| 81 | TRS1 (TRS) | Temperature coefficient (linear) for RS | 0 | ${ }^{\circ} \mathrm{K}^{-1}$ |
| 82 | TRS2 | Temperature coefficient (quadratic) for RS | 0 | ${ }^{\circ} \mathrm{K}^{-2}$ |
| 83 | TRSH1 | Temperature coefficient (linear) for RSH | 0 | ${ }^{\circ} \mathrm{K}^{-1}$ |
| 84 | TRSH2 | Temperature coefficient (quadratic) for RSH | 0 | ${ }^{\circ} \mathrm{K}^{-2}$ |
| Noise Effect Related Model Parameters |  |  |  |  |
| 85 | AF | Flicker noise exponent | 1 |  |
| 86 | KF | Flicker noise coefficient | 0 |  |
| 87 | FLKLEV | Flicker noise level selector | 0 |  |

Table 4-36. MOSFET Common Parameters

| Nr. | Name | Description | Default | Units |
| :--- | :--- | :--- | :--- | :--- |
| 88 | THMLEV | Thermal noise level selector | 0 |  |
| Geometric Range Related Model Parameters |  |  |  |  |
| 89 | WMIN | Model geometric range parameters. These model <br> parameters give the range of the physical length and <br> width dimensions to which the MOSFET model applies; <br> used in conjunction with binning models | 1 | $\mu \mathrm{~m}$ |
| 90 | WMAX |  | 1 | $\mu \mathrm{~m}$ |
| 91 | LMIN |  | 100 | $\mu \mathrm{~m}$ |
| 92 | LMAX |  |  |  |

1. The model parameter OPTACM, when set to 1 , has the same effect as .option ACM. The only difference is that the latter affects all of the model cards in the netlist, while the former affects the model card that it is specified in.
2. The model parameter CALCACM will accept either 0 (default) or 1 . It is used only with .option ACM or OPTACM=1, and $A C M=12$. By default (CALCACM=0), sets the value of ALEV to 0 but if it is set to 1 , it ALEV will be set to 2 .
3. for $\mathbf{A L E V}=7$, the definition is "total width connection."
4. if $\mathbf{T L E V}=0$ or $1, \mathbf{E G}=1.11$, else $\mathbf{E G}=1.16$
*. For parameters marked with a * in their default parameter column, the default value depends upon the model selected, see tables below.

Table 4-37. RLEV Default Values

| Model (Eldo Level) | RLEV default value |
| :--- | :--- |
| Level (12,13,16,17), BSIM1 (8) | 0 |
| EKV (44) | 2 |
| BSIM3v2 (47), BSIM3v3 (53) | 4 |
| Level (1,2,3), MOS9 (53), BSIM2 (11), MM11 (63,65) | 6 |

Table 4-38. ALEV Default Values

| Model (Eldo Level) | ALEV default value |
| :--- | :--- |
| Level (12,13,16,17), BSIM1 (8), BSIM3v3 (53) | 0 |
| EKV (44), BSIM3v2 (47) | 2 |
| Level (1,2,3), MOS9 (53), BSIM2 (11), MM11 (63,65) | 6 |

Table 4-39. DIOLEV Default Values

| Model (Eldo Level) | DIOLEV default value |
| :--- | :--- |
| Level (1,2,3), MOS9 (53), BSIM3v2 (47) | 1 |
| Level (12,13,16,17), | 2 |
| BSIM1 (8), BSIM2 (11) | 3 |

Table 4-39. DIOLEV Default Values

| Model (Eldo Level) | DIOLEV default value |
| :--- | :--- |
| EKV (44) | 6 |
| BSIM3v3 (53) | 7 |
| MM11 (63,65) | 9 |

Table 4-40. DCAPLEV Default Values

| Model (Eldo Level) | DCAPLEV default value |
| :--- | :--- |
| Level (12,13,16,17), BSIM1 (8) | 0 |
| BSIM3v2 (47) | 1 |
| Level (1,2,3), MOS9 (53), BSIM2 (11), EKV (44) | 2 |
| BSIM3v3 (53) | 4 |
| MM11 (63,65) | - |

## Scaling Rules

$$
\begin{array}{lr}
L D I F_{\text {scal }}=L D I F \cdot \text { scalm } & H D I F_{\text {scal }}=H D I F \cdot \mathrm{scalm} \\
D L_{\text {scal }}=D L \cdot \mathrm{scalm} & D W_{\text {scal }}=D W \cdot \mathrm{scalm} \\
L D_{\text {scal }}=L D \cdot \mathrm{scalm} & W D_{\text {scal }}=\mathrm{WD} \cdot \mathrm{scalm} \\
A D_{\text {scal }}=\frac{A D}{\mathrm{scalm} \cdot \mathrm{scalm}} & A S_{\text {scal }}=\frac{\mathrm{AS}}{\mathrm{scalm} \cdot \mathrm{scalm}} \mathrm{vtvt} \\
P D_{\text {scal }}=\frac{P D}{\mathrm{scalm}} & P S_{\text {scal }}=\frac{P S}{\mathrm{scalm}} \\
J S_{\text {scal }}=\frac{\mathrm{JS}}{\mathrm{scalm} \cdot \mathrm{scalm}} & J S W_{\text {scal }}=\frac{\mathrm{JSW}}{\mathrm{scalm}} \\
C J_{\text {scal }}=\frac{C J}{\mathrm{scalm} \cdot \operatorname{scalm}} & C J S W_{\text {scal }}=\frac{C J S W}{\mathrm{scalm}} \\
C J G A T E_{\text {scal }}=\frac{C J G A T E}{\mathrm{scalm}} &
\end{array}
$$

## Note

The model parameter scaling factor SCALM can be defined for all model cards in the netlist using . OPtion SCALM=val, or can be individually defined for each model card using the model parameter sCALM. This overrides the global sCALM value defined using the .OPTION command.

## Berkeley SPICE Models

The DC characteristics of the MOSFET are defined by the device parameters VTO, Kp, LAMBDA, phi and gamma. These are computed by Eldo, if the process parameters (nSUB, tox, ...) are given. User specified values always override calculated values. vто is positive (negative) for enhancement mode and negative (positive) for depletion mode N -channel (P-channel) devices.

Charge storage is modeled by three constant capacitors, cGSo, cGDO and cgbo. Capacitances taken into account are the non-linear thin-oxide capacitance distributed among the gate, source, drain and bulk regions, and the non-linear depletion-layer capacitances for both substrate junctions divided into bottom and periphery, which vary as the mJ and mJSw power of junction voltage respectively, and are determined by the parameters CBD, CBS, CJ, CJSw, MJ, MJSw and pb. The model is the piecewise linear voltage dependent capacitance model proposed by Meyer.

Some overlap among the parameters describing the junctions exists, for example Reverse current can be input either as is (in Amperes) or as Js (in $\mathrm{Am}^{-2}$ ). The first is an absolute value, while the second is multiplied by $\boldsymbol{A D}$ and $\operatorname{As}$ to give the reverse current of the drain and source junctions respectively. This methodology is used as there is no sense in always relating junction characteristics with $A D$ and as of the device card; these areas can be defaulted. The same idea also applies to the zero-bias junction capacitances CBD and CBS (in Farads) on one hand, and CJ (in $\mathrm{Fm}^{-2}$ ) on the other. Parasitic drain and source series resistance can be expressed as either RD and RS (in $\Omega$ ) or $\mathbf{R S H}$ (in $\Omega /$ Square), the latter being multiplied by the number of squares NRD and NRS input on the device card.

The temperature of a semiconductor model can be defined in Eldo using the тмор parameter. If this parameter is not present the global circuit temperature $\boldsymbol{T N O M}$ is assumed. The individual model temperature of a device can be set by using the optional instance parameter $\boldsymbol{\tau}$.


Please refer to the MOS Level 1, 2, 3 Equations of the Eldo Device Equations Manual. For model parameters, please refer to the Berkeley SPICE Model (Eldo Level 1, 2, 3) Parameters of the Eldo Device Equations Manual.

Specific Levels 1, 2, and 3 initialization for parasitics common approach MOS parameters:

- ALEV=6; RLEV=6; DIOLEV=1; DCAPLEV=2
if xJ is specified then $\mathrm{LD}=0.75 \times \mathrm{xJ}$ otherwise $\mathrm{LD}=0$;
- Equivalent name definitions:

PHP parameter is equivalent to PBSW.
xL and xw are equivalent to DL and DW respectively.

For details of the common parameters, see "MOS Parasitics Common Approach" on page 258.

## MERCKEL MOSFET Models

Three Merckel model levels are presently available as Levels 4, 5 and 6. These models are defined by their own set of parameters, which can be easily extracted from measurements.

## Note

$\square$ Contact Mentor Graphics for more details about the above models.

## Key Parameters

- vto

Threshold voltage at vGS $=0$.

- muo

Low field surface mobility.

- D

Correction term issued from development of the ' $3 / 2$ ' model. D is extracted from the model parameter.

- TG

Gate field effect coefficient on mobility.

- TD

Drain field effect coefficient on mobility, which equals $\frac{M U O}{(L \times V S)}$ where VS is the saturation velocity.

- VEA

Early voltage coefficient.
The Level 4 model is a charge control model and the DC characteristics are the same as in Level 6.

The Level 5 model is very similar to that of SPICE Level 1, but it also takes into account the effect of mobility modulation by $\boldsymbol{T G}$. The early effect is modeled by $\mathbf{K e}$ instead of LAMBDA as in SPICE models.

The Level 6 model is more accurate, and it is especially dedicated to submicron technologies; the threshold dependencies on geometries are modeled by ve instead of Lambda as in SPICE models.

The capacitance models are close to those of SPICE. The bulk junction capacitances vary with the power of $-1 / 2$ of the junction voltage. Overlap capacitances are computed from the REC parameter. LDIF is used for computation of the drain and source perimeters and areas, if the parameters for $\mathbf{A D}, \mathbf{A S}, \mathbf{P D}$ and $\mathbf{P S}$ are missing in the declaration of the MOS transistor.

1 Please refer to the MOS Level 4, 5, 6 Equations of the Eldo Device Equations Manual. For model parameters, please refer to the MERCKEL MOSFET Model (Eldo Level 4, 5, 6) Parameters of the Eldo Device Equations Manual.

For flklev and thmlev, see the "Noise in MOSFETs" on page 256.

## Correspondence of Merckel to SPICE Model Parameters

For historical reasons, some SPICE parameter names have equivalent Merckel parameter names, which can be interchanged within a model definition. The following is a list of these parameters:

Table 4-41. Merckel-Spice

| Merckel | SPICE |
| :--- | :--- |
| NIV | LEVEL |
| EOX | TOX |
| DPHIF | PHI |
| VTO | VT0 |
| MUO | UO |
| KB | GAMMA |
| TG | THETA |
| NB | NSUB |
| CDIFS0 | CJSW |
| CDIFP0 | 2 LD |
| DL | KP/2 |
| KO |  |

## Berkeley SPICE BSIM1 Model (Eldo Level 8)

The Berkeley Short Channel IGFET Model (BSIM1) is a semi-empirical model proposed by the University of Berkeley (California). It was adopted to cope with rapid advances of technologies and fits well for submicron technologies.

The major effects modeled in BSIM1 include:

- mobility reduction due to the vertical field
- channel length modulation
- carrier velocity saturation
- non-uniform channel doping
- subthreshold conduction
- drain-induced barrier lowering
- source/drain charge sharing

A representation with 17 parameters per device size was found to be adequate for modeling the DC characteristics. Geometric dependencies are included to introduce parameter sensitivity to length and width. The charge model was derived from its drain-current counterpart to ensure model consistency of device physics. Charge conservation is also guaranteed. Also, three possible drain-source sharings are possible.
(i)

Please refer to the BSIM1 Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the Berkeley SPICE BSIM1 Model (Eldo Level 8)
Parameters of the Eldo Device Equations Manual.

Specific BSIM1 initialization for parasitics common approach MOS parameters:
ALEV=0; RLEV=0; DIOLEV=3; DCAPLEV=0
if xJ is specified then $\mathrm{LD}=0.75 \times \mathrm{xJ}$ otherwise $\mathrm{LD}=0$;

For details of the common parameters, see "MOS Parasitics Common Approach" on page 258.

## Berkeley SPICE BSIM2 Model (Eldo Level 11)

Based on BSIM1 model, the BSIM2 was developed by the University of Berkeley (California) to correct BSIM1 problems. BSIM2 has been successfully used to model the drain current and output resistance of MOSFETs with gate oxide as thin as 3.6 nm and channel length as small as $0.2 \mu \mathrm{~m}$.

Based on recent physical understanding of deep-submicron MOSFETs, it has been found that the important effects that should be included in MOSFET modeling are:

- mobility reduction due to the vertical field
- carrier velocity saturation
- non-uniform channel doping
- subthreshold conduction
- drain-induced barrier lowering
- source/drain charge sharing
- channel length modulation
- source/drain parasitic resistance
- hot electron induced output resistance reduction
- inversion layer capacitance.

Except for the three last effects, most of these were already present in the BSIM1 model. In order to develop a consistent model, these effects were re-examined using new deep-submicron MOSFET considerations and their implementation. The charge model was derived from its drain-current counterpart to ensure model consistency of device physics. Charge conservation is also guaranteed. Also 3 possible drain-source sharings are possible.

## (i)

Please refer to the BSIM2 Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the Berkeley SPICE BSIM2 Model (Eldo Level 11) Parameters of the Eldo Device Equations Manual.

Specific BSIM2 initialization for parasitics common approach MOS parameters:
ALEV=6; RLEV=0; DIOLEV=3; DCAPLEV=2
if xJ is specified then $\mathrm{LD}=0.75 \times \mathrm{xJ}$; otherwise $\mathrm{LD}=0$;
$\mathbf{C J}=0$; $\mathbf{F C}$ is not a BSIM2 parameter, therefore it is set to 0 . page 258.

## Modified Berkeley Level 2 (Eldo Level 12)

A modified version of Level 2, Level 12 includes specification of Meyer capacitance parameters Cf1, CF2, CF3, CF5 and cgbex. These parameters are used to solve the dynamic part of the model. The diode currents, impact ionization currents and access resistances are also calculated differently when using this model.

Please refer to the Modified Berkeley Level 2 (Eldo Level 12) of the Eldo Device Equations Manual.
For model parameters, please refer to the Modified Berkeley SPICE Level 2 Parameters of the Eldo Device Equations Manual.

## Modified Berkeley Level 3 (Eldo Level 13)

A modified version of Level 3, Level 13 includes specification of Meyer capacitance parameters CF1, CF2, CF3, CF5 and cgbex. These parameters are used to solve the dynamic part of the model. The diode currents, impact ionization currents and access resistances are also calculated differently when using this model.

## 1 Please refer to the Modified Berkeley Level 3 (Eldo Level 13) of the Eldo Device Equations Manual.

For model parameters, please refer to the Modified Berkeley SPICE Level 3 Parameters of the Eldo Device Equations Manual.

## Example

```
*MOSFET model definition
.model me21 nmos level=4 vtO=1v eox=25n uo=600
+ nsub=2.0e16 phi=0.6 vmax=2.0e5 kw=2.24u
+ kl=2.24u gw=3.91u gl=0.7u dinf=0.1 kb=0.1
+ ve=1.0e4 ldif=10u cj=0.0001 cjsw=0 dw=0
+ dl=0.8u rec=0.15u tg=0.06
*main circuit
m1 vdd n3 n2 vbb me21 w=40u l=3u
```

Specifies the transistor m1 with a 40 micron channel width, a 3 micron channel length, drain connected to node vdd, gate to node n3, Source to node n2 and bulk to voltage vbb. The electrical parameters are specified in the model me21.

## Modified Lattin-Jenkins-Grove Model (Eldo Level 16)

Level 16 model, also called Lattin-Jenkins-Grove model, is a model based on Level 2 equations and represents the ASPEC, ISPICE compatible model.

Please refer to the Modified Lattin-Jenkins-Grove Model (Eldo Level 16) of the Eldo Device Equations Manual.
For model parameters, please refer to the Modified Lattin-Jenkins-Grove Model Parameters of the Eldo Device Equations Manual.

## Enhanced Berkeley Level 2 Model (Eldo Level 17)

An enhanced version of Berkeley Level 2, Level 17 includes modified equations for the description of the threshold voltage, subthreshold current, effective mobility and effective substrate doping.

The additional developments of the standard Berkeley SPICE Level 2 Model in this Eldo Level 17 are derived from model equations developed by the General Electric/Intersil Research Institutes.

Please refer to the Enhanced Berkeley Level 2 Model (Eldo Level 17) of the Eldo Device Equations Manual.
For model parameters, please refer to the Enhanced Berkeley SPICE Level 2 Model Parameters of the Eldo Device Equations Manual.

## EKV MOS Model (Eldo Level 44 or EKV)

The EKV model was originally developed by the EPFL (Ecole Polytechnique Fédérale de Lausanne), namely MM Enz, Krummenacher and Vittoz, hence the name. It is the result of many years of investigation to find a model that deals correctly with analog problems. Consequently, it may solve the problems of analog designers mainly in low voltage and low current applications and in terms of realistic behavior for currents, conductances and capacitances.

A compatible version of the EKV model is available in Eldo. This signifies that former versions of the model are also available. The compatibility covers versions v2.3 up to, and including, the new v2.6 (revision 2). The different versions are accessible through the model parameter update which can be used as shown in the table below. By default, the EKV model version v 2.3 is selected.

Table 4-42. EKV MOS Models

| Parameter Value | EKV Version |
| :--- | :--- |
| UPDATE $=2.3$ or UPDATE $=23$ | EKV v2.3 (Default) |
| UPDATE $=2.5$ or UPDATE $=25$ | EKV v2.5 |
| UPDATE $=2.61$ or UPDATE $=26.1$ | EKV v2.6 (Revision 1) |
| UPDATE $=2.6$ or UPDATE $=26$ <br> UPDATE $=2.62$ or UPDATE $=26.2 ~$ | EKV v2.6 (Revision 2) |
| UPDATE=2.63 or UPDATE $=26.3$ | EKV v2.6 (Revision 3) |

## Note

EKV versions v1.3 and v2.2 are no longer supported.

Please refer to the EKV MOSFET Equations of the Eldo Device Equations Manual. For model parameters, please refer to the EKV MOS Model (Eldo Level 44) Setup Parameters and EKV MOS Model (Eldo Level 44) Parameters of the Eldo Device Equations Manual.
Please refer to the Parameter units and Parameter preprocessing (intrinsic parameters initialization, version 2.6 revision 2) of the Eldo Device Equations Manual.

## Berkeley SPICE BSIM3v2 Model (Eldo Level 47)

BSIM3 version 2 is a physical model developed by the University of Berkeley (California). It is based on a coherent quasi two-dimensional analysis of the MOSFET device structure, taking into account the effects of device geometry and process parameters. It allows users to accurately model MOSFET behavior for up-to-date submicron technologies.

Please refer to the BSIM3v2 Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the Berkeley SPICE BSIM3v2 Model (Eldo Level 47) Parameters of the Eldo Device Equations Manual.

## Notes about Parameters

- npeak, ngate, nd and uo may be entered in meters or centimeters:

NPEAK is converted to $\mathrm{cm}^{-3}$ as follows: if nPEAK is greater than $1 \times 10^{20}$, it is multiplied by $1 \times 10^{-6}$.
nGATE is converted to $\mathrm{cm}^{-3}$ as follows: if nGATE is greater than $1 \times 10^{23}$, it is multiplied by $1 \times 10^{-6}$.
ND is converted to $\mathrm{cm}^{-3}$ as follows: if ND is greater than $1 \times 10^{24}$, it is multiplied by $1 \times 10^{-6}$.
vo is converted to $\mathrm{m}^{2}(\mathrm{Vs})^{-1}$ as follows: if vo is greater than 1 , it is multiplied by $1 \times 10^{-4}$.
nsub must be entered in $\mathrm{cm}^{-3}$.

- Specific BSIM3v2 initialization for parasitics common approach MOS parameters:

ARLEV=ALEV=2; RLEV=4; DCAPLEV=1; DIOLEV=1.
CJ= $5 \times 10^{-4} ;$ CJSW= $=5 \times 10^{-10} ; \mathrm{PB}=1 ;$ PBSW=1;
FC is not a BSIM3v2 parameter, therefore it is set to 0 .
As a consequence, you may use LD, wD instead of DL, Dw. Respectively, if DL, DW are given, they will be used for common equation initializations instead of $L D$ and wD.

For details of the common parameters, see the "MOS Parasitics Common Approach" on page 258.

- For derivative computation in BSIM3v2, a parameter deriv has been added. By default, Deriv=1 for analytical derivatives. Deriv may be set to 0 (or with the command .option mnumer) for the finite difference method.


## Berkeley SPICE BSIM3v3 Model (Eldo Level 53)

BSIM3v3 has been extensively modified from its previous release BSIM3v2. The physical effects modeled are the same as BSIM3v2. In addition to those, the new advancements are:

- A single drain current expression to describe current and output conductance characteristics from subthreshold to strong inversion as well as from the linear to the saturation operating region,
- New width dependencies for bulk charge and source/drain resistance ( $\boldsymbol{R d s}$ ),
- New capacitance models for both intrinsic and extrinsic capacitances,
- A new noise model,
- A new relaxation time model for characterizing the non-quasi-static effect for improved transient modeling.

Please refer to the BSIM3v3 Equations of the Eldo Device Equations Manual.

BSIM3v3 is available in four versions: BSIM3v3, BSIM3v3.1, BSIM3v3.2, and the most recent, BSIM3v3.3. According to Berkeley's recommendation, version BSIM3v3.2 is split into four versions.

All the different versions are accessible through the model parameter ver. By default, BSIM3v3.2.4 (ver=3.24) is selected.

Table 4-43. BSIM3v3 Models

| Parameter Value | BSIM3v3 Version |
| :--- | :--- |
| VER $($ VERSION $)=3.3$ | BSIM3v3.3 |
| VER(VERSION $)=3.24$ | BSIM3v3.2.4 (Default) |
| VER(VERSION $)=3.23$ | BSIM3v3.2.3 |
| VER $($ VERSION $)=3.22$ | BSIM3v3.2.2 (Also if vER $=3.2$ ) |
| VER $($ VERSION $)=3.21$ | BSIM3v3.2.1 |
| VER $($ VERSION $)=3.1$ | BSIM3v3.1 |
| VER $($ VERSION $)=3.0$ | BSIM3v3 |

## BSIM4 gate current inside BSIM3v3

Due to the continual decrease in device dimensions, the oxide thickness in new technologies is very small, so much so that the gate current is noticeable. Many companies would model the gate current with BSIM3v3 model in the form of a SUBCKT, however, this would slow the simulation a great deal. The gate current model of BSIM4 has, therefore, been incorporated inside BSIM3v3.

Having the gate current inside the compact model should be much faster than in the form of a SUBCKT. The model parameters used in BSIM4 should be used for the gate current. The two main selectors are IGCMOD \& IGBMOD. If either of these flags equal 1, the gate current will be calculated and the values taken will not be equal to 0 . If both of these selectors are equal to 0 or not specified, the gate current is not calculated and the simulation will proceed as before.

These parameters can be found in the BSIM4 Gate Current Model parameter table.

## BSIM4 Gate-Induced Drain and Source Leakage Current inside BSIM3v3

The gate induced drain leakage (GIDL) and gate induced source leakage (GISL) currents are gaining more importance in new technologies from day to day. Many companies would model the GIDL current with BSIM3v3 model, using a SUBCKT, however, this would slow the simulation. The GIDL (and GISL, see Note below) current model of BSIM4 has therefore been incorporated inside BSIM3v3 to increase the simulation speed. The model parameters used in BSIM4 should be used for the GIDL current. These four main parameters are AGIDL, BGIDL, CGIDL \& EGIDL. If any of these parameters are specified using the model command, the GIDL current will be calculated. If none of the parameters are specified however, the GIDL current is not calculated and the simulation will proceed as before.

These parameters can be found in the BSIM4 Gate-Induced Drain Leakage Model Parameters table.

## Note

BSIM4.21 has the addition of Gate Induced Source Leakage (GISL) current. This is enabled by default in BSIM3v3 when enabling the GIDL current. If you want to use the GIDL model of BSIM4 versions prior to version 4.21, please set the IGIDLVER model parameter to a value less than 4.21 (default value). See the BSIM4.2.1 enhancements for further information on the GISL in BSIM4.

## BSIMSOI3 DTOXCV Parameter inside BSIM3v3

There have been a number of problems regarding $\boldsymbol{C A P M O D}=3$ of BSIM 3 v 3 . The most serious symptom is the capacitance reduction (Cgg) in the strong inversion region if CAPMOD was
changed from 0 to 3. BSIMPD is an SOI model formulated on top of the BSIM3v3 framework and also has the same trouble. The Berkeley team proposed an additional parameter, DTOXCV, in $\boldsymbol{C A P M O D}=3$ of BSIMPDv2.2.3 to solve this issue. This has also been added to BSIM3v3.

This parameter can be found in the Process Parameters section of the parameter table.

## Compatibility option for negative Rds values

By default, negative $\boldsymbol{R} \boldsymbol{d} \boldsymbol{s}$ values are clipped to zero. An Eldo option is available to allow negative Rds values: . OPTION RDSWTPOS=0|1. Default value is 1 , which means Eldo clips negative $\boldsymbol{R} d \boldsymbol{s}$ values (after temperature update) to zero. To allow negative $\boldsymbol{R} \boldsymbol{d} \boldsymbol{s}$ values, set the option to 0 .

## Caution

When this option is used to allow negative $\boldsymbol{R} \boldsymbol{d} \boldsymbol{s}$ values, the results may be unpredictable, or even cause the simulation to fail.

For model parameters, please refer to the Berkeley SPICE BSIM3v3 Model (Eldo Level 53) Parameters of the Eldo Device Equations Manual.

## Notes about Parameters

- nch, ngate and uo may be entered in meters or centimeters:
$\mathbf{N C H}$ is converted to $\mathrm{cm}^{-3}$ as follows: if NCH is greater than $1 \times 10^{20}$, it is multiplied by $1 \times 10^{-6}$.
ngate is converted to $\mathrm{cm}^{-3}$ as follows: if ngate is greater than $1 \times 10^{23}$, it is multiplied by $1 \times 10^{-6}$.
vo is converted to $\mathrm{m}^{2} / \mathrm{Vsec}$ as follows: if vo is greater than 1 , it is multiplied by $1 \times 10^{-4}$.
nsub must be entered in $\mathrm{cm}^{-3}$.
- Specific BSIM3v3 initialization for parasitics common approach MOS parameters:

ARLEV=ALEV=0; RLEV=4; DCAPLEV=1; DIOLEV=1.
CJ= $5 \times 10^{-4} ;$ CJSW=5 $\times 10^{-10} ; \mathrm{PB}=1$; PBSW= 1 ;
FC is not a BSIM3v3 parameter, therefore it is set to 0 .
As a consequence, you may use LD, wD instead of LINT, WINT or DL, Dw instead of dLc, DWc. Respectively, LINT, wINT and DLc, DWC will be used for common equation initialization.

For details of the common parameters, see the "MOS Parasitics Common Approach" on page 258.

- As $\boldsymbol{L I N T}$ and $\boldsymbol{L} \boldsymbol{D}$ are both the same the user should only specify one parameter (LINT or $\boldsymbol{L D})$. If both $\boldsymbol{L I N T}$ and $\boldsymbol{L D}$ are specified then Eldo will return the following warning:

```
Double definition for parameter(s) LD.
```

Only the value of $\boldsymbol{L D}$ will be printed in the .chi file.

- For derivative computation in BSIM3v3, a parameter deriv has been added. By default, Deriv= $=1$ for analytical derivatives. Deriv may be set to 0 (or with the command .option mnumer) for the finite difference method.
- The different versions, BSIM3v3.2, BSIM3v3.1 and BSIM3v3, can also be selected by using the command. option bsim3ver $=3.2,3.1$ or 3.0.
- Parameter checking is added in BSIM3v3.2 to avoid bad values of certain parameters as follows:
If $\operatorname{PSCBE} 2 \leq 0.0$, the user will be warned for the poor value used.
If (MOIN <5.0) or (MOIN > 25.0), a warning message will be given.
If $(\boldsymbol{A C D E}<0.4)$ or ( $\boldsymbol{C} \boldsymbol{C D E}>1.6$ ), a warning message will be given.
If $(\boldsymbol{N O F F}<0.1)$ or $(\boldsymbol{N O F F}>4.0)$, a warning message will be given. If ( $\boldsymbol{V O F F C V}<-0.5$ ) or ( $\boldsymbol{V O F F C V}>0.5$ ), a warning message will be given.
If ( $\boldsymbol{I J T H}<0.0$ ), fatal error occurs. If ( $\boldsymbol{T O X M}<=0.0$ ), fatal error occurs


## Printing and plotting BSIM3v3 Output States

The three capacitance states can be printed/plotted for any BSIM3v3 instance using the syntax S (Mxx->state). For example, $C A P G D O$ can be printed by specifying:

```
.PLOT DC S (Mxx->CAPGDO) for DC or
.PLOT AC S (Mxx->CAPGDO) for AC or
.PLOT TRAN S (Mxx->CAPGDO) for TRAN
```

Table 4-44. Berkeley BSIM3v3 States

| State | Description |
| :--- | :--- |
| CAPGDO | Gate-Drain overlap capacitance |
| CAPGSO | Gate-Source overlap capacitance |
| CAPGBO | Gate-Bulk overlap capacitance |

## Motorola SSIM Model (Eldo Level 54 or SSIM)

This model is only supported on Solaris platforms in Eldo 32-bit mode.
The Motorola SSIM model can be invoked in two ways:

- By specifying explicitly the level SSim inside the .model card:

```
.MODEL mod NMOS LEVEL=SSIM <end of the model ...>
```

or:
.MODEL mod NMOS LEVEL=54 <end of the model ...>

- By running Eldo in Motorola mode:
- by invoking Eldo with the -ssim switch at runtime, or
- by adding . OPtion motorola at the beginning of the netlist (before the first .MODEL card).

When Eldo is in Motorola mode, the level of the SSIM model is 6 :

```
.MODEL mod NMOS LEVEL=6
```

Note
This is useful when the user wants to utilize a .model card from Motorola. The same system exists for the STMicroelectronics models.

## Berkeley SPICE BSIMSOI3 v1.3 Model (Eldo Level 55)

BSIMSOI3 v1.3 is an officially released SOI (Silicon On Insulator) MOSFET model from the Device Group at the University of California at Berkeley. The model can be used for both Partially Depleted (PD) and Fully Depleted (FD) devices. Many advanced concepts are introduced so as to allow transition between PD and FD operation dynamically and continuously, namely the Dynamic Depletion Approach. The basic I-V model is modified from the BSIM3v3.1 equation set.

Please refer to the BSIMSOI3 v1.3 Equations of the Eldo Device Equations Manual.

## Command Line Information

```
Mname <D node> <G node> <S node> <E node> [P node] <model>
+ [\mathbf{L}=<\mathrm{ VAL >] [W=<VAL>]}
+ [\mathbf{AD}=<\textrm{VAL}>] [\mathbf{AS}=<\textrm{VAL}>] [PD=<VAL>] [PS=<VAL>]
+ [NRS=<VAL>] [NRD=<VAL>] [NRB=<VAL>]
+ [OFF] [BJTOFF=<val>] [RTHO=<VAL>] [CTHO=<VAL>]
+ [M=<VAL>] [DEBUG=<VAL>]
```


## Parameters

- D node

Drain node

- G node

Gate node

- S node

Source node

- E node

Substrate node

- [P node]

Optional external body contact
if not specified, it is a 4-terminal device
if specified, it is a 5-terminal device. The $P$ node and $B$ node will be connected by a resistance.

- model

Level 55 BSIMSOI3 model name

- $\mathrm{L}=\mathrm{VAL}$

Channel length

- $\mathbf{w}=$ VAL

Channel width

- $\mathrm{AD}=\mathrm{VAL}$

Drain diffusion area

- $\boldsymbol{A S}=\mathrm{VAL}$

Source diffusion area

- $P D=V A L$

Drain diffusion perimeter length

- $\mathbf{P S}=\mathrm{VAL}$

Source diffusion perimeter length

- NRS=VAL

Number of squares in source series resistance

- NRD=VAL

Number of squares in drain series resistance

- $\quad$ nRB=VAL

Number of squares in body series resistance

- off=VAL

Device simulation off

- BJTOFF=VAL

Turn off BJT current if equal to 1

- RTHO=VAL

Thermal resistance per unit width
if not specified, RTHO is extracted from the model card.
if specified, it will override the one in the model card.

- CTHO=VAL

Thermal capacitance per unit width
if not specified, стно is extracted from model card.
if specified, it will over-ride the one in model card.

- $\mathbf{M}=$ VAL

This is the device "multiplier," simulating the effect of multiple devices in parallel.
Effective width, overlap, junction capacitances, and junction currents are multiplied by m. Parasitic resistance values are divided by m. Default value is 1 .

- DEBUG=VAL

Please see the notes below.

## Printing/Plotting States

The instance parameter debug allows users to turn on debugging information selectively. Internal parameters (for example par) for an instance (for example m1) can be plotted by this command:

```
.plot <Analysis_Type> S(m1 -> par)
```


## Example

```
.plot DC S(m1 -> body)
```


## Berkeley SPICE BSIMSOI3 v2.x and v3.x Model (Eldo Level 56)

BSIMSOI3 is the officially released SOI (Silicon On Insulator) MOSFET model from the Device Group at the University of California at Berkeley. Both BSIMSOI v2.x and v3.x models can be used for Partially Depleted (PD) and Fully Depleted (FD) devices. For the BSIMSOIv2.x model many advanced concepts were introduced so as to allow transition between PD and FD operation dynamically and continuously, namely the Dynamic Depletion Approach (DD). The user is able to select one of these three modes using a parameter selector called SOIMOD. The basic I-V model is modified from the BSIM3v3.1 equation set.

The different versions are accessible through the model parameter version as shown in the table below. By default, BSIMSOI3v3.2 (version=3.2) is selected.

Table 4-45. BSIMSOI3 Version Selection

| Parameter Value | BSIMSOI3 Version |
| :--- | :--- |
| VERSION $=3.2$ | BSIMSOI3v3.2 (Default) |
| VERSION $=3.11$ | BSIMSOI3v3.1.1 |
| VERSION $=3.1$ | BSIMSOI3v3.1 |
| VERSION $=3.0$ | BSIMSOI3v3.0 |
| VERSION $=2.23$ | BSIMSOI3v2.2.3 |
| VERSION $=2.22$ | BSIMSOI3v2.2.2 |
| VERSION $=2.21$ | BSIMSOI3v2.2.1 |
| VERSION $=2.1$ | BSIMSOI3v2.1 |

Parameter selector soimod was an Eldo specific model parameter in the v2.x versions. Beginning version v3.0, it is a Berkeley standard model parameter to select between various SOI models: PD, FD and DD. For versions v3.0 and v3.1, the soimod values have changed in Eldo to be compatible with the Berkeley standard values. Please see the following table:

> Table 4-46. SOIMOD Selection

| Model | SOIMOD for v2.x <br> (Eldo specific) | SOIMOD for v3.0 <br> (Spice compatible) | SOIMOD for v3.1 <br> (Spice compatible) |
| :--- | :--- | :--- | :--- |
| PD | 1 | 0 (default) | 0 (default) |
| DD | 2 (default) | - | - |
| FD | 3 | - | 2 |
| FD module over PD $^{1}$ | - | 1 | 1 |

1. The FD module is an addition of some equations over the PD module to make the PD module also fit FD devices.

The different versions are handled separately inside this chapter. See "BSIMPDv2.x" on page 282, "BSIMFDv2.1" on page 282, "BSIMDDv2.1" on page 282, and "BSIMSOI3v3.x" on page 282.

The major features are summarized as follows:

- Dynamic depletion approach is applied on both I-V and C-V. Charge and Drain current are scalable with $\boldsymbol{T B O X}$ and $\boldsymbol{T S I}$ continuously.
- Supports external body bias and backgate bias; a total of 6 nodes.
- Real floating body simulation in both I-V and C-V. Body potential is properly bounded by diode and C-V formulation.
- Self heating implementation improved over the alpha version.
- An improved impact ionization current model.
- Various diode leakage components and parasitic bipolar current included.
- New depletion charge model ( $\boldsymbol{E B C I}$ ) introduced for better accuracy in capacitive coupling prediction. An improved BSIM3v3 based model is also included.
- Dynamic depletion can suit different requirements for SOI technologies.
- Single I-V expression as in BSIM3v3.1 to guarantee the continuity of $I_{d s}, G_{d s}$ and $G_{m}$ and their derivatives for all bias conditions.


## TNODEOUT keyword

tnodeout is a keyword that can be specified in the instantiation statement of an SOI device as follows:

Mxx nd ng ns ne <np> <nb> <nT> mname <L=val> <W=val> TNODEOUT

- If tnodeout is not specified, the user can specify four nodes for a device with floating body. Specifying five nodes implies that the fifth node is the external body contact node, with a body resistance between the internal and external terminals. This configuration applies to a distributed body resistance simulation. Specifying six nodes implies a body contacted case with an accessible internal body node (sixth node). Specifying seven nodes implies that the seventh node is the temperature node. This may be used to model thermal coupling.
- If tnodeout is specified, simulation interprets the last node as the temperature node. You can specify five nodes for a device with floating body. Specifying six nodes implies body contact. Seven nodes is a body contacted case with an accessible internal body node.


## VBSUSR keyword

VBSUSR is a keyword which allows you to set the transient initial condition of the body potential $\left(\boldsymbol{V}_{\boldsymbol{b}}\right)$. For example:

```
.MODEL nnn NMOS LEVEL=56
m1 11 2 0 0 b nnn VBSUSR=1.5
```


## BSIMSOI3v2.x

## BSIMPDv2.x

BSIMPD is a Partially Depleted (PD) Silicon-on-Insulator (SOI) MOSFET model for SPICE simulation. This model is formulated on top of the BSIM3v3 framework. It shares the same basic equations with the bulk model so that the physical nature and smoothness of BSIM3v3 are retained. Most parameters related to general MOSFET operation (non-SOI specific) are directly imported from BSIM3v3 to ensure parameter compatibility.

Many enhanced features are included in BSIMPD through the joint effort of the BSIM Team at UC Berkeley and IBM Semiconductor Research and Development Center (SRDC) at East Fishkill. In particular, the model has been tested extensively within IBM on its state-of-the-art high speed SOI technology.

The latest version, BSIMPDv3.1.1, is implemented in Eldo. A version control parameter VERSION allows the use of older versions if required.

For model parameters, please refer to the Berkeley SPICE BSIMSOI3 PD Model (Eldo Level 56) Parameters of the Eldo Device Equations Manual.

## BSIMFDv2.1

For model parameters, please refer to the Berkeley SPICE BSIMSOI3 FD v2.1 Model (Eldo Level 56) Parameters of the Eldo Device Equations Manual.

## BSIMDDv2.1

For model parameters, please refer to the Berkeley SPICE BSIMSOI3 DD Model (Eldo Level 56) Parameters of the Eldo Device Equations Manual.

## BSIMSOI3v3.x

Using BSIMPD as a foundation, a unified model is implemented for both PD and FD SOI circuit designs based on the concept of body-source built-in potential lowering.

In this version, BSIMSOI is constructed based on the concept of body-source built-in potential lowering, $\Delta V_{b i}$. There are three modes (soiMod $\left.=0,1,2\right)$ in BSIMSOI: BSIMPD $(\boldsymbol{s o i M o d}=0)$ can be used to model the PD SOI device, where the body potential is independent of $\Delta V_{b i}\left(V_{B S}\right.$ $>\Delta V_{b i}$ ). Therefore the calculation of $\Delta V_{b i}$ is skipped in this mode. On the other hand, the ideal FD model $(\boldsymbol{s o i M o d}=2)$ is for the FD device with body potential equal to $\Delta V_{b i}$. Hence the calculation of body current/charge, which is essential to the PD model, is skipped. For the unified SOI model (soiMod $=1$ ), however, both $\Delta V_{b i}$ and body current/charge are calculated to capture the floating-body behavior exhibited in FD devices.

## BSIMSOIv3.x Parameter List

For model parameters, please refer to the BSIMSOIv3.x Parameter List of the Eldo Device Equations Manual.

## Philips MOS 9 Model (Eldo Level 59 or MOSP9)

Philips MOS 9 model is a compact model for MOS transistor, intended for the simulation of circuit behavior with emphasis on analog applications. This model has been developed originally by Philips Electronics, N.V and is now in the public domain.

Please refer to the MOS Model 9 Equations of the Eldo Device Equations Manual.

The implementation in Eldo is based on the unclassified report NL-UR 003/94 "MOS MODEL 9, level 902" issued in June 1995. The current implementation is MOS Model 9, level 903. In addition to the Philips syntax for the parameters, some equivalences to common approach parameters are made:

```
philips = eldo
LVAR = DL
LAP = LD
WVAR = DW
WOT = WD
NFR = KF
TR = TNOM
```

In these cases, the same default values are used.
Additionally, all the parameters available for the common approach are available for this model together with the corresponding equations set for parasitics. Furthermore, AF slope for noise has been added in Eldo. The overlap capacitances may be defined through the Philips parameter COL or through CGDO, CGSO. CGBO is also introduced.

The instantiation parameter mult that indicates the number of devices in parallel is called $\mathbf{m}$ in Eldo.

The present restrictions in Eldo w.r.t. Philips implementation is that noise equations only include $\boldsymbol{S} \boldsymbol{f l}$ and $\boldsymbol{S t h}$ terms.

The model parameter version can be set to values of 903.1 (default) or 903.2. When set to 903.2, it allows the model parameter the3R to take negative values, otherwise the3R is clipped to zero if negative.

Table 4-47. Philips MOS9 Version Selection

| Parameter Value | Effect on THE3R |
| :--- | :--- |
| VERSION $=903.1$ | Clip тHE3R to zero if negative |
| VERSION $=903.2$ | Allows тHe3R to take negative values |

For model parameters, please refer to the Philips MOS 9 Model (Eldo Level 59) Reference and Scaling Parameters of the Eldo Device Equations Manual.

## Berkeley SPICE BSIM4 Model (Eldo Level 60)

The possible versions of this model are BSIM4.0.0, BSIM4.1.0, BSIM4.2.0, BSIM4.2.1, BSIM4.3.0, BSIM4.4.0, BSIM4.5.0, BSIM4.6.0, BSIM4.6.1, BSIM4.6.2, BSIM4.6.3, and BSIM4.6.4 (default).

Note
BSIM4 accepts the M factor.

According to the model developers, Berkeley, the BSIM4 model has been developed to explicitly address many issues in modeling sub- 0.13 micron CMOS technology and RF highspeed CMOS circuit simulation.

Please refer to the BSIM4 Equations of the Eldo Device Equations Manual.

## Use of Juncap diode (DIOLEV=9.0) with BSIM4

The Juncap diode ( $\operatorname{DIOLEv}=9$ ) can be used as a parasitic diode for the BSIM4 MOSFET model instead of that provided by Berkeley.

The Juncap diode can be chosen by specifying the model card parameter diolev=9.0. Values for diolev other than 9.0 will give a warning and the diode quantities will be calculated using the Berkeley parasitic diodes.

The parameters and equations of the Juncap diode (diolev= 9.0) can all be found in the section Level 8 Equations of the Eldo Device Equations Manual.

## Note

The initialization of device parameters ( $P S, A S, P D, A D$ ) and calculation of geometrical quantities (PSeff, ASeff, PDeff, ADeff) are all Berkeley standard for BSIM4; not those of the common equations.

## BSIM4 Model Selection via W/L Specifications

The BSIM4 model has unique conditions for W/L specification model selection. See "Selection of MOSFET Models via W/L Specifications (Binning)" on page 257.

The different BSIM4 versions are accessible through the model parameter VERSION. By default, BSIM4.6.4 (VERSION=4.64) is selected.

Table 4-48. Berkeley BSIM4 Version Selection

| Parameter Value | BSIM4 Version |
| :--- | :--- |
| VERSION $=4.64$ | BSIM4.6.4 (Default) |
| VERSION $=4.63$ | BSIM4.6.3 |
| VERSION $=4.62$ | BSIM4.6.2 |
| VERSION $=4.61$ | BSIM4.6.1 |
| VERSION $=4.6$ | BSIM4.6.0 |
| VERSION $=4.5$ | BSIM4.5.0 |
| VERSION $=4.4$ | BSIM4.4.0 |
| VERSION $=4.3$ | BSIM4.3.0 |
| VERSION $=4.21$ | BSIM4.2.1 |
| VERSION $=4.2$ | BSIM4.2.0 |
| $V E R S I O N=4.1$ | BSIM4.1.0 |
| $V E R S I O N=4.0$ | BSIM4.0.0 |

## BSIM4.x Model Parameters

- For model parameters, please refer to the Berkeley BSIM4 Model (Eldo Level 60) Parameters of the Eldo Device Equations Manual.
- For BSIM4.4.0 model parameters, please refer to the Berkeley BSIM4.4.0 Specific Model Parameters of the Eldo Device Equations Manual.
- For BSIM4.5.0 model parameters, please refer to the Berkeley BSIM4.5.0 Specific Model Parameters of the Eldo Device Equations Manual.
- For BSIM4.6.0 model parameters, please refer to the Berkeley BSIM4.6.0 Specific Model Parameters of the Eldo Device Equations Manual.
- For BSIM4.6.1 model parameters, please refer to the Berkeley BSIM4.6.1 Specific Model Parameters of the Eldo Device Equations Manual.
- For BSIM4.6.2 model parameters, please refer to the Berkeley BSIM4.6.2 Specific Model Parameters of the Eldo Device Equations Manual.


## EKV3 MOS Model (Eldo Level 61 or EKV3)

The EKV model was originally developed by the EPFL (Ecole Polytechnique Fédérale de Lausanne), namely MM Enz, Krummenacher and Vittoz, hence the name. The EKV3 model is a MOSFET model that has five modes of operation, each mode covers the needs of certain cases.

The possible versions of this model are EKV301_01 and EKV301_02 (default).

(i)Please refer to the EKV3 MOSFET Model of the Eldo Device Equations Manual. For model parameters, please refer to the EKV3 MOS Model (Eldo Level 61) Parameters of the Eldo Device Equations Manual.

## TFT Polysilicon Model (Eldo Level 62)

This is the modified polysilicon TFT model based on the original work at Rensselaer Polytechnic Institute (RPI).

This is a complete model developed for CAD and is based on the new universal charge control concept which guarantees stability and conversion. The unified DC model covers all regimes of operation and the AC model accurately reproduces frequency dispersion of capacitances (because of low mobility, carrier transit time is quiet; the signal period for even low frequency signals). This model provides automatic scaling of model parameters to accurately model a wide range of device geometries and physical based parameters can be easily extracted from experimental data.
i
Please refer to the TFT Polysilicon Model of the Eldo Device Equations Manual. For model parameters, please refer to the TFT Polysilicon Model (Eldo Level 62) Parameters of the Eldo Device Equations Manual.

## Philips MOS Model 11 Level 1101 (Eldo Level 63)

A new compact model for MOS transistors has been developed. Philips MOS Model 11 (MM11), the successor of Philips MOS Model 9, not only gives an accurate description of charges and currents and their first-order derivatives (transconductance, conductance, capacitances), but also of their higher-order derivatives. In other words it gives an accurate description of MOSFET distortion behavior, and as such MM11 is suitable for digital, analog as well as RF circuit design.

MOS Model 11 is a symmetrical, surface-potential-based model. It includes an accurate description of all physical effects important for modern and future CMOS technologies, such as, for example, gate tunnelling current, influence of pocket implants, poly-depletion, quantummechanical effects and bias-dependent overlap capacitances.

Level 1101 is an updated version of Level 1100. It uses the same basic equations as Level 1100, but uses different geometry scaling rules. It includes two types of geometrical scaling rules: physical rules and binning rules. Moreover, the temperature scaling has been implemented on the "miniset" level instead of the "maxiset" level as was the case for Level 1100.

The MM11 model (Level 1101) is implemented in Eldo as LEVEL=63.

For information on the MM11 model (Level 1100), see Philips MOS Model 11 Level 1100 (Eldo Level 65).

Binning is used with this MM11 Level 1101 to decide which geometrical scaling rule is used. For Physical rule binning $=0.0$ and for Binning rule binning $=1.0$. By Default binning $=0.0$ (Physical rule) is used.

Table 4-49. Philips MOS Model 11 Version Selection

| Parameter Value | Geometrical scaling rule |
| :--- | :--- |
| BINNING=0.0 | Physical rule (Default) |
| BINNING=1.0 | Binning rule |

## Model Parameters

MM11 Level 1101(0) is specified with Binning=0.0 (Physical rule).
For model parameters, please refer to the MM11 Level 1101(0) Model Parameters Physical Rule of the Eldo Device Equations Manual.

MM11 Level 1101(1) is specified with binning $=1.0$ (Binning rule).
For model parameters, please refer to the MM11 Level 1101(1) Model Parameters Binning Rule of the Eldo Device Equations Manual.

## TFT Amorphous-Si Model (Eldo Level 64)

This is the modified amorphous-silicon TFT model based on the original work at Rensselaer Polytechnic Institute (RPI).

The model provides the following features and benefits:

- Uses the new, universal charge control concept, which guarantees stability and convergence
- Unified DC models cover all regimes of operation
- AC models accurately reproduces $\boldsymbol{C g} \boldsymbol{c}$ frequency dispersion
- Automatic scaling of model parameters to accurately model a wide range of device geometries
- Temperature dependence included
- A minimum number of physically based parameters that can easily be extracted from experimental data and related back to the fabrication steps


## Printing or plotting a state from the TFT A-Si States structure

If a state from the list below is to be monitored by the user, the user has to type in the netlist for a given transistor M1 to monitor, for example Gm:

```
.PLOT DC S(M1->Gm) for DC or
.PLOT AC S (M1->Gm) for AC or
.PLOT TRAN S(M1->Gm) for TRAN
```


## Philips MOS Model 11 Level 1100 (Eldo Level 65)

A new compact model for MOS transistors has been developed. Philips MOS Model 11 (MM11), the successor of Philips MOS Model 9, not only gives an accurate description of charges and currents and their first-order derivatives (transconductance, conductance, capacitances), but also of their higher-order derivatives. In other words it gives an accurate description of MOSFET distortion behavior, and as such MM11 is suitable for digital, analog as well as RF circuit design.

MOS Model 11 is a symmetrical, surface-potential-based model. It includes an accurate description of all physical effects important for modern and future CMOS technologies, such as, for example, gate tunnelling current, influence of pocket implants, poly-depletion, quantummechanical effects and bias-dependent overlap capacitances.

There are two versions of this model. Level 1100 and Level 1101. Level 1101 is an updated version of Level 1100.

The MM11 model (Level 1100) is implemented in Eldo as LEVEL=65.
For information on the MM11 model (Level 1101), see Philips MOS Model 11 Level 1101 (Eldo Level 63).

Please refer to the MOS Model 11 Level 1100 \& 1101 Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the MM11 Level 1100 Model (Eldo Level 65) Parameters of the Eldo Device Equations Manual.

## HiSIM Model (Eldo Level 66)

According to the model developers, HiSIM (Hiroshima University STARC IGFET Model) is the first complete surface-potential-based MOSFET model for circuit simulation based on the drift-diffusion approximation.

The most important advantage of the surface-potential-based modeling is the unified description of device characteristics for all bias conditions. The physical reliability of the drift-diffusion approximation has been proved by 2D device simulations with channel lengths even down to below $0.1 \mu \mathrm{~m}$. To obtain analytical solutions for describing device performances, the charge sheet approximation of the inversion layer with zero thickness has been introduced. Together with the gradual-channel approximation all device characteristics are then described analytically by the channel-surface potentials at the source side ( $\phi_{\mathrm{S} 0}$ ) and at the drain side ( $\phi_{\mathrm{SL}}$ ). These surface potentials are functions of applied voltages on the four MOSFET terminals; the gate voltage $\mathrm{V}_{\mathrm{g}}$, the drain voltage $\mathrm{V}_{\mathrm{d}}$, the bulk voltage $\mathrm{V}_{\mathrm{b}}$ and the reference potential of the source $\mathrm{V}_{\mathrm{s}}$. This is the long-channel basis of the HiSIM model, and extensions of the model approximations are done for advanced technologies. All newly appearing phenomena such as short-channel and reverse-short-channel effects are included in the surface potential calculations causing modifications resulting from the features of these advanced technologies.

HiSIM versions are accessible through the model parameter VERSION. By default, HiSIM2.4.3 (VERSION=243) is selected, Table 4-50 shows how to select the other available versions.

Table 4-50. HiSIM Version Selection

| Parameter Value | HiSIM Version |
| :--- | :--- |
| VERSION $=243$ | HiSIM2.4.3 (Default) |
| VERSION $=242$ | HiSIM2.4.2 |
| VERSION $=241$ | HiSIM2.4.1 |
| VERSION $=240$ | HiSIM2.4.0 |

Table 4-50. HiSIM Version Selection

| Parameter Value | HiSIM Version |
| :--- | :--- |
| VERSION $=231$ | HiSIM2.3.1 |

Please refer to the HiSIM Model of the Eldo Device Equations Manual. For model parameters, please refer to the HiSIM (Eldo Level 66) Model Parameters of the Eldo Device Equations Manual.

## SP Model (Eldo Level 67)

SP is a generic compact MOSFET model developed at The Pennsylvania State University. It is surface-potential-based, free from unphysical behavior often associated with more traditional models and contains a relatively small number of parameters. The development of SP is based on solution of several long standing problems of compact MOSFET modeling.

Consequently SP is a surface potential based model that does not contain iterative loops or channel segmentation in both the intrinsic and the extrinsic submodels.

Please refer to the Surface-Potential-Based Compact MOSFET Model of the Eldo Device Equations Manual.
For model parameters, please refer to the Ranges of SP Parameters, Temperature dependence (-55 to 150), and Extrinsic Model Parameters of the Eldo Device Equations Manual.

## Philips MOS Model 11 Level 1102 (Eldo Level 69)

MOS Model 11 (MM11, level 1102) is a new compact MOSFET model, intended for digital, analog and RF circuit simulation in modern and future CMOS technologies. MM1102 gives not only an accurate description of currents and charges and their first-order derivatives (i.e. transconductance, conductance, capacitances), but also of the higher order derivatives, resulting in an accurate description of electrical distortion behavior. The latter is especially important for analog and RF circuit design. The model furthermore gives an accurate description of the noise behavior of MOSFETs. Additionally, in order for the model to be valid for modern and future MOS devices, several important physical effects have been included in the model.

MM1102, is an updated version of MM1101. It uses slightly different equations. The surface potential generally is implicitly related to the terminal voltages and has to be calculated iteratively. Since the iterative procedure was assumed to be time consuming, the surface potential has been approximated by an explicit expression in MM1101. In the MM1102, the surface potential is calculated iteratively using a second-order Newton-Raphson procedure, resulting in a much more accurate description of surface potential which is obtained within three iterations. Owing to the increased accuracy, some of the basic equations used in MM1101 can
be simplified, and as a result MM1102 is computationally as fast as MM1101. In addition, a more physical and simpler velocity saturation expression is used, and as a consequence the saturation voltage expression has changed slightly as well. This all results in a more accurate description of transconductance in saturation.

The MM11 model (Level 1102) is implemented in Eldo as LEVEL=69.

Please refer to the MOS Model 11 Level 1102 Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the MM11 Level 1102 Model Parameters (Electrical), MM11 Level 11020 Model Parameters (Physical), and MM11 Level 11021 Model Parameters (Binning) of the Eldo Device Equations Manual.

## Philips PSP Model (Eldo Level 70)

The PSP model is a new compact MOSFET model, which has been jointly developed by Philips Research and Penn State University (currently under development in Arizona State University). It is a surface-potential based MOS Model, containing all relevant physical effects (mobility reduction, velocity saturation, DIBL, gate current, lateral doping gradient effects, and so on) to model present-day and upcoming deep-submicron CMOS technologies. Unlike previous Philips MOS models, the source/drain junction model, c.q. the JUNCAP2 model, is an integrated part of the PSP model.

The PSP model is a symmetrical, surface-potential-based model, giving an accurate physical description of the transition from weak to strong inversion. The PSP model includes an accurate description of all physical effects important for modern and future CMOS technologies

In addition, it gives an accurate description of charges and currents and their first-order derivatives (transconductance, conductance, capacitances), but also of their higher-order derivatives. In other words, it gives an accurate description of MOSFET distortion behavior, and as such the PSP model is suitable for digital, analog as well as RF circuit design.

PSP model versions are accessible through the VERSION model parameter. The possible values of VERSION are listed in Table 4-54.

Table 4-51. PSP Version Selection

| Parameter Value | PSP Version |
| :--- | :--- |
| VERSION $=102.33$ | PSP 102.3.3 (Default) |
| VERSION $=102.32$ | PSP 102.3.2 |
| VERSION $=102.3$ | PSP 102.3 |
| VERSION $=102.21$ | PSP 102.2.1 |
| VERSION $=102.2$ | PSP 102.2 |

Table 4-51. PSP Version Selection

| Parameter Value | PSP Version |
| :--- | :--- |
| VERSION $=102.1$ | PSP 102.1 |
| VERSION $=102.0$ | PSP 102.0 |

©
Please refer to the PSP Model Equations of the Eldo Device Equations Manual. For model parameters, please refer to the Parameter Scaling and Parameter Sets of the Eldo Device Equations Manual.

## Philips MOS Model 20 Level 2002 (Eldo Level 71)

According to the model developers, Philips, MOS Model 20 (MM20) is a new compact MOSFET model, intended for analog circuit simulation in high-voltage MOS technologies. MOS Model 20 describes the electrical behavior of the region under the thin gate oxide of a high-voltage MOS device, like a Lateral Double-diffused MOS (LDMOS) device or an extended-drain MOSFET. It thus combines the MOSFET-operation of the channel region with that of the drift region under the thin gate oxide in a high-voltage MOS device. As such, MOS Model 20 is aimed as a successor of the combination of MOS Model 9 (MM9) for the channel region in series with MOS Model 31 (MM31) for the drift region under the thin gate oxide, in macro models of various high-voltage MOS devices.

Note
$\square$ The MM20 level 2001 model is not supported.

The MOS Model 20 (MM20, level 2002.2) is implemented in Eldo as LEVEL=71.

Please refer to the MOS Model 20 Level 2002 Equations of the Eldo Device Equations Manual.
For model parameters, please refer to the MM20 Level 2002 Geometrical Model Parameters (Eldo Level 71) of the Eldo Device Equations Manual.

## Berkeley SPICE BSIMSOI4.0 Model (Eldo Level 72)

BSIMSOI is a SPICE compact model for SOI (Silicon-On-Insulator) circuit design. According to the model developers, Berkeley, the BSIMSOI4.0 model is formulated on top of the BSIM3 framework. It shares the same basic equations with the bulk model so that the physical nature and smoothness of BSIM3v3 are retained. BSIMSOI4.0 addresses several new issues in modeling sub- 0.13 micron CMOS/SOI high-speed and RF circuit simulation. BSIMSOI4.0 is fully backward compatible with its previous 3.x version.

The BSIMSOI4.0 model is implemented in Eldo as LEVEL=72.
BSIMSOI4 model versions are accessible through the VERSION model parameter. The possible values of VERSION are listed in Table 4-52.

Table 4-52. BSIMSOI4 Version Selection

| Parameter Value | BSIMSOI4 Version |
| :--- | :--- |
| Version $=4.2$ | BSIMSOI4.2 (Default) |
| Version $=4.0$ | BSIMSOI4.0 |

## HiSIM-LDMOS Model (Eldo Level 73)

HiSIM-LDMOS has been developed as an extension of HiSIM for conventional MOSFETs. According to the model developers, HiSIM (Hiroshima University STARC IGFET Model) is the first complete surface-potential-based MOSFET model for circuit simulation based on the drift-diffusion approximation.

HiSIM-LDMOS shares some significant equations with the HiSIM Model but has differences due to the drift region and self-heating. For information on HiSIM, see "HiSIM Model (Eldo Level 66)" on page 289.

The most important advantage of the surface-potential-based modeling is the unified description of device characteristics for all bias conditions. The physical reliability of the drift-diffusion approximation has been proved by 2D device simulations with channel lengths even down to below $0.1 \mu \mathrm{~m}$. To obtain analytical solutions for describing device performances, the charge sheet approximation of the inversion layer with zero thickness has been introduced. Together with the gradual-channel approximation all device characteristics are then described analytically.

The most important feature of LDMOS, different from the conventional MOSFET, is originated by the drift region introduced to achieve high voltage applications. By varying the length as well as a concentration of the drift region, various devices with various operating bias conditions are realized.

The HiSIM-LDMOS model is implemented in Eldo as LEVEL=73.

HiSIM-LDMOS versions are accessible through the VERSION model parameter. By default, HiSIM-LDMOS/HV 1.1.1 (VERSION=111) is selected. Table 4-53 shows the model parameter values for the available versions.

Table 4-53. HiSIM-LDMOS Version Selection

| Parameter Value | HiSIM-LDMOS/HV Version |
| :--- | :--- |
| VERSION $=111$ or 1.11 | HiSIM-LDMOS/HV 1.1.1 (Default) |
| VERSION $=110$ or 1.10 | HiSIM-LDMOS/HV 1.1.0 |
| VERSION $=102$ or 1.02 | HiSIM-LDMOS/HV 1.0.2 |
| VERSION $=101$ or 1.01 | HiSIM-LDMOS/HV 1.0.1 |
| VERSION $=100$ or 1.00 | HiSIM-LDMOS/HV 1.0.0-SC3 |

Please refer to the HiSIM-LDMOS Model of the Eldo Device Equations Manual. For model parameters, please refer to the HiSIM-LDMOS (Eldo Level 73) Model Parameters of the Eldo Device Equations Manual.

## MOSVAR Model (Eldo Level 74)

According to the model developers, the MOS varactor compact model is based in part on the PSP MOSFET model and is intended for analogue and RF design. It includes dynamic inversion, finite poly doping, quantum mechanics, tunneling currents, and parasitics to model advanced MOS technologies.

The MOSVAR device is instantiated in Eldo as a 3-terminal MOSFET.
The MOSVAR model has been implemented in Eldo as LEVEL=74.
MOSVAR model versions are accessible through the VERSION model parameter. The possible values of VERSION are listed in Table 4-54.

Table 4-54. MOSVAR Version Selection

| Parameter Value | MOSVAR Version |
| :--- | :--- |
| VERSION $=1.1$ | MOSVAR 1.1 (Default) |
| VERSION $=1.0$ | MOSVAR 1.0 |

Please refer to the MOSVAR Model of the Eldo Device Equations Manual.
For model parameters, please refer to the MOSVAR (Eldo Level 74) Model Parameters of the Eldo Device Equations Manual.

## PSP103 Model (Eldo Level 75)

There are two versions of this model; PSP 103.0 and PSP 103.1 (the default).
According to the joint-developers, NXP Semiconductors Research (formerly part of Philips) and Arizona State University (formerly at The Pennsylvania State University), the PSP (Version 103.0) model is a new compact MOSFET model. The roots of PSP lie in both MOS Model 11 (Philips) and SP (Penn State). PSP is a surface-potential based MOS Model, containing all relevant physical effects (mobility reduction, velocity saturation, DIBL, gate current, lateral doping gradient effects, STI stress, etc.) to model present-day and upcoming deep-submicron bulk CMOS technologies. The source/drain junction model (the JUNCAP2 model) is fully integrated in PSP.

PSP not only gives an accurate description of currents, charges, and their first order derivatives (i.e. transconductance, conductance and capacitances), but also of the higher order derivatives, resulting in an accurate description of electrical distortion behavior. The latter is especially important for analog and RF circuit design. The model furthermore gives an accurate description of the noise behavior of MOSFETs. Finally, PSP has an option for simulation of non-quasi-static (NQS) effects.

Please refer to the PSP103 Model Equations of the Eldo Device Equations Manual. For model parameters, please refer to the Parameter Scaling and Parameter Sets of the Eldo Device Equations Manual.

## HVMOS Model (Eldo Level 101)

The HV (High-Voltage) MOS transistor model is based on the BSIM3v3 model. Major enhancements include current-crowding effect at high gate bias, asymmetric source-drain structure, self-heating, and more flexible gate-dependent output characteristics. Like BSIM3v3, the HVMOS transistor model also allows the binning option to achieve even higher accuracy. The binning equation is given by:

$$
P=P 0+\frac{P l}{\text { Leff }}+\frac{P w}{W e f f}+\frac{P p}{\text { Leff } \cdot W e f f}
$$

[^4]
## HVMOS License

The HVMOS model is a proprietary model of Cadence Design Systems, Inc. To use the HVMOS model, a license for Eldo from Mentor Graphics is required, as well as a license for the HVMOS model from Cadence.

To setup the license daemon for the HVMOS library, please refer to BTA's "License Installation and Management User Guide."
(1) Please refer to the HVMOS Model of the Eldo Device Equations Manual.

For model parameters, please refer to the HVMOS Model (Eldo Level 101) Parameters of the Eldo Device Equations Manual.

## S-Domain Filter

FNSxx IN OUT [RIN=val] [ROUT=val] NN \{NN\}, DN \{DN\}
The Eldo S-Domain filter is defined by the Transfer Function:

$$
H(s)=\frac{N_{0}+N_{1} s+N_{2} s^{2}+N_{3} s^{3}+\ldots+N_{n} s^{n}}{D_{0}+D_{1} s+D_{2} s^{2}+D_{3} s^{3}+\ldots+D_{m} s^{m}}
$$

## Parameters

- $x x$

S-Domain filter name.

- IN

Name of the input node.

- out

Name of the output node.

- RIN

Input resistance. Default is infinity. This resistance of value RIN is located between node in and ground. Note that setting RIn to 0 will have the default effect, i.e. that RIn will be infinity.

- rout

Output resistance. Default is 0.0. FNS output is equivalent to a voltage source in series with an output resistance rout.

- NN

Coefficients of the Transfer Function numerator, starting from $N_{0}$.

- DN

Coefficients of the Transfer Function denominator, starting from $D_{0}$.

## Example

```
fns1 n1 n2 1 2, 1 3 2
```

Specifies an S-Domain filter fns1 with input and output nodes n1 and n2. The Transfer Function is:

$$
H(s)=\frac{1+2 s}{1+3 s+2 s^{2}}
$$

It is possible to specify the order of the coefficient in brackets after giving the coefficient value. All non-specified coefficients will be set to 0 , for example:

```
fns2 1 2 rout=1 1.0e0(0), 1.0e0(0) 3.0e-8(1) 1.0e-16(3)
```

Device Models
S-Domain Filter
is equivalent to:

$$
\text { fns2 } 12 \text { rout=1 } 1.0 e 0,1.0 e 03.0 e-801.0 e-16
$$

## Z-Domain Filter

FNZxx IN OUT FREQ=VAL [RIN=val] [ROUT=val] NN \{NN\}, DN \{DN\}
The Eldo Z-Domain filter is defined by the Transfer Function:

$$
H(z)=\frac{N_{0}+N_{1} z^{-1}+N_{2} z^{-2}+N_{3} z^{-3}+\ldots+N_{n} z^{-n}}{D_{0}+D_{1} z^{-1}+D_{2} z^{-2}+D_{3} z^{-3}+\ldots+D_{m} z^{-m}}
$$

## Parameters

- xx

Z-Domain filter name.

- IN

Name of the input node.

- OUT

Name of the output node.

- FREQ=VAL

Sampling frequency in Hertz.

- RIN

Input resistance. Default is infinity. This resistance of value RIN is located between node in and ground. Note that setting RIn to 0 will have the default effect, i.e. that RIN will be infinity.

- rout

Output resistance. Default is 0.0 . FNZ output is equivalent to a voltage source in series with an output resistance rout.

- NN

Coefficients of the Transfer Function numerator, starting from $N_{0}$.

- DN

Coefficients of the Transfer Function denominator, starting from $D_{0}$.
The AC response of $Z$ transforms was modified, beginning Eldo v6.3, to be consistent with that of ADMS. The term $\sin x / x$ is taken into account by Eldo. Use the option nozsinxx to remove the effect of that term for pre-v6.3 functionality.

## Example

```
fnz1 n1 n2 freq=1k 1 3, 1 2 4
```

A Z-Domain filter fnz1 with input and output nodes n1 and n2, clocked at 1 kHz . The Transfer Function is:

$$
H(z)=\frac{1+3 z^{-1}}{1+2 z^{-1}+4 z^{-2}}
$$

It is possible to specify the order of the coefficient in brackets after giving the coefficient value. All non-specified coefficients will be set to 0 , for example:

```
fnz2 1 2 freq=1k rout=1 1.0e0(0), 1.0e0(0) 3.0e-8(1) 1.0e-16(3)
```

is equivalent to:

```
fnz2 1 2 freq=1k rout=1 1.0e0, 1.0e0 3.0e-8 0 1.0e-16
```


## Subcircuit Instance

```
Xxx NN {NN} NAME [PAR=VAL] [PAR={EXPR}] [M=VAL] [TEMP=VAL] [DTEMP=VAL]
+ [STATISTICAL=0|1] [(ANALOG|OSR|DIGITAL)] [NONOISE|NOISE=0]
Xxx [MODEL:] MNAME PIN: {pin=net}
+ PARAM: {par=val} KEYWORD: {keywords} [STATISTICAL=0|1]
Xxx [MODEL:] MNAME NET: {net=pin}
+ PARAM: {par=val} KEYWORD: {keywords} [STATISTICAL=0|1]
```

This statement is used to instantiate a subcircuit that has been previously defined using a . subckt command. Subcircuit definitions and instances can be nested. Parameters contained in a subcircuit can be assigned explicitly or via the .PARAM command, direct assignment always taking precedence over .PARAM commands.

The first syntax above shows pins mapped by position. The second syntax above shows pins mapped by name. Usually, pins of subcircuit (X) instances are supposed to be specified in the order corresponding to that of the . subckт declaration (first syntax). However, it is also possible to instantiate a subcircuit (X) using pin names of a . SUвскт definition (second syntax), providing that option xbyname is set. The third syntax is similar to the second, with nets mapped to pins.

In order to improve execution speed the subcircuit can be optionally solved using the differentiated accuracy system.

Before using this system, refer to "Speed and Accuracy" on page 1061.

## Parameters

- xx

Subcircuit name.

- NN

Names of the nodes to be connected externally. Nodes are referenced in the order they appear in a .subckt command.

- NAME

Name of the subcircuit being instantiated, as specified by the . subckt command.

- $\quad$ PAR=VAL

Specifies that the parameter PAR is assigned the value VAL inside the subcircuit. This parameter assignment takes precedence over any parameter assignments occurring in the .SUBCKT command.

- $\mathbf{M}=\mathrm{VAL}$

Multiplication factor for the subcircuit instantiation. This effectively places m instances of the subcircuit in parallel, all connected to the specified nodes NN . If $\mathbf{m}=0$ is specified, the corresponding subcircuit instance will be ignored (as if the subcircuit instance is commented out). Every element defined in the subcircuit will be duplicated by this multiplication factor.

- TEMP = VAL

Sets temperature for the individual subcircuit. This overrides the temperature of devices which are instantiated in the X instance. Default nominal temperature $=27^{\circ} \mathrm{C}$.

- $\mathbf{D T E M P}=\mathrm{VAL}$

Temperature difference between the devices in the subcircuit and the rest of the circuit, in degrees Celsius. Default value is 0.0 .

## Note

TEMP and DTEMP are mutually exclusive. If both are specified, the last one is used.

- StATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the subcircuit instance. 0 means the subcircuit components will keep their nominal values. 1 means the subcircuit components have statistical variation applied. The global default can be specified via option Statistical. Default is 1 .

- (ANALOG)

Keyword used with the differentiated accuracy system indicating that the subcircuit should be solved using Newton block iteration techniques. These techniques are used in conjunction with the eps parameter in the .OPTION command. (ANALOG) basically means "high accuracy."


Before using the differentiated accuracy system see the relevant section in "Speed and Accuracy" on page 1061.

- (OSR|DIGITAL)

Used to stop propagation of the ANALOG flag across the hierarchy. In addition the flag will request Eldo to use OSR in the selected blocks, if possible (i.e. MOS subcircuit with OSR flag could then be solved by OSR, but BJT subcircuit will still be solved by Newton even if flag OSR is set).

- NONOISE

Specifies that no noise model will be used for this subcircuit when performing noise analysis. Therefore, the subcircuit presents no noise contribution to the noise analysis. For more details see ".SUBCKT" on page 898. Can also be specified between parentheses as (NONOISE) or with NOISE=0.

- NOISE=0

Synonymous with nonoise keyword. Specifies that no noise model will be used for this subcircuit when performing noise analysis. Therefore, the subcircuit presents no noise contribution to the noise analysis. Specifying any value other than zero will cause Eldo to issue a warning, and the parameter will be ignored.

- [MODEL:] MNAME

Name of the subcircuit being instantiated, as specified by the . subckt command.

- PIN: \{pin=net \} NET: \{net=pin\}

A list of pins to be mapped by name. pin is the name of the pin as declared in a . subckт command. net is the name of the node to be connected externally ("parent" name). Eldo also accepts NET: in place of PIN:, in which case the order is reversed, Eldo will first expect the actual net named followed by the pin name as it appears in the . suвскт command.

- PARAM: \{par=val\}

Specifies that the parameter PAR is assigned the value VAL inside the subcircuit. This parameter assignment takes precedence over any parameter assignments occurring in the . SUBCKт command.

- KEYWORD: \{keywords\}

Allows specification of a list of keywords: SWITCH, ANALOG, OSR, DIGItAL.

## Notes for pins mapped by name syntax

- When mapping pins by name, keywords pin:, PARAM:, and keyword: are mandatory in order to separate the different fields.
- Fields cannot be split, the same keyword cannot appear twice in the same X instance.
- Fields can be specified in any order.
- Eldo will issue an error if some mappings are missing in the PIN: or NET: declarations.
- When option xbyname is set, it is possible to mix both syntaxes in the same netlist, Eldo will check for the presence of at least one of the keywords PIN:, PARAM:, NET:, MODEL: , or KEYWORD: to select which syntax to be used for each X instance. See option "XBYNAME" on page 962.


## Combining Identical Subcircuits

Multiple identical subcircuit instances connected in parallel are reduced into a single instance using the $\boldsymbol{m}$ parameter, for example:

$$
\begin{array}{llllll}
\mathbf{x} 1 & 1 & 2 & \text { FOO } & A=1 & B=1 \\
\mathbf{x} & 1 & 2 & F O O & A=1 & B=1
\end{array}
$$

x3 12 FOO $\mathrm{A}=1.0 \mathrm{~B}=1$
Here, $x 3$ will remain as it is because the character string for A does not match, but X instances x 1 and x 2 will be replaced by:
$\mathbf{x} 112 \mathrm{FOO} \mathrm{A}=1 \quad \mathrm{~B}=1 \quad \mathrm{M}=2$

For more information see "Merging Devices in Parallel" on page 120.

## Examples

```
*SUBCKT definition
.subckt inv 1 2
r1 1 3 2k
r2 3 4 4k
r3 4 2 3k
.ends inv
*subcircuit instance
x1 1 48 inv
.print v(x1.1)
.plot v(x1.1)
```

Specifies the instantiation of subcircuit inv with instance name x1 placed between nodes 1 and 48. Subcircuit node 1 is shown both printed and plotted.

```
*SUBCKT definition
.subckt inv 1 2
r1 1 3 rval
r2 3 4 rval1
r3 4 2 rval2
.ends inv
...
*subcircuit instance
x1 1 2 inv rval=6 rval2={rval1+1k}
.param rval1 = 10
x2 2 3 inv rval=4
.ic v(x1.1)=0
```

Specifies two instantiations of subcircuit inv with instance names x1 and x2. Parameters are assigned directly, using expressions and via the .PARAM command. Subcircuit node 2 is given the initial condition of 0 V via the . Ic command.

Usually, pins of subcircuit (X) instances are supposed to be specified in the order corresponding to that of the . Subckт declaration (pins mapped by position). For instance, in the following:

```
.SUBCKT foo A B
.ends
X1 P1 P2 foo p1=1
```

then A is mapped to P 1 and B to P 2 .

However, it is also possible to instantiate a subcircuit (X) using pin names of a . subckт definition (pins mapped by name), providing that option xbyname is set. The example above can be rewritten as:

```
.option xbyname
.SUBCKT foo A B
.ends
X1 foo PARAM: p1=1 PIN: B=P2 A=P1
```

The following example shows how to instantiate a subcircuit (X) using pin names (pins mapped by name) and using net names (nets mapped by pin), providing that option xbyname is set:

```
.option XBYNAME
.subckt inv2 a y
X1 a net1 inv ln=0.18u wn=2.0u lp=0.18u wp=4.0u
X2 net1 y inv ln=0.18u wn=2.0u lp=0.18u wp=4.0u
.ends
X1 in out1 inv2
X2 MODEL: inv2 PIN: a=in y=out2
X3 MODEL: inv2 NET: in=a out3=y
XTOP in out inv2
```

The following example shows how the DTEMP parameter is used to specify a difference between the circuit temperature and the subcircuit instance temperature. In this example Eldo will assume that the temperature of devices inside X 1 will be $40+10=50^{\circ} \mathrm{C}$ :

```
.subckt r 1 2
r1 1 2 1 tc1=1
.ends
i1 1 0 1
x1 1 0 r dtemp = 10
.TEMP 40
.op
.end
```

Device Models Subcircuit Instance

## Chapter 5 Sources

## Introduction

Eldo provides a number of sources (stimuli generators) which can be divided into four groups as shown below:

## Independent Sources

Two types of independent sources are provided:

$$
\begin{array}{lc}
\text { Independent Voltage Source } & \text { V } \\
\text { Independent Current Source } & \mathrm{I}
\end{array}
$$

Independent sources can be assigned a time-dependent value for transient analysis. The time zero values of time dependent sources are used for DC analysis. Eight types of time dependent source are provided:

| Amplitude Modulation Function | AM |
| :--- | :--- |
| Exponential Function | EXP |
| Noise Function | NOISE |
| Noise Table Function | NOISE TABLE |
| Pattern Function | PATTERN |
| Pulse Function | PULSE |
| Piece Wise Linear Function | PWL |
| Single Frequency FM Function | SFFM |
| Sine Function | SIN |
| Trapezoidal Pulse With Bit Pattern Function | PBIT |
| Exponential Pulse With Bit Pattern Function | EBIT |

## Linear Dependent Sources

Four types of linear dependent sources are provided:

| Linear Voltage Controlled Voltage Source $(\mathrm{v}=\mathrm{e} \cdot \mathrm{v})$ | E |
| :--- | :--- |
| Linear Current Controlled Current Source $(\mathrm{i}=\mathrm{f} \cdot \mathrm{i})$ | F |
| Linear Voltage Controlled Current Source $(\mathrm{i}=\mathrm{g} \cdot \mathrm{v})$ | G |
| Linear Current Controlled Voltage Source $(\mathrm{v}=\mathrm{h} \cdot \mathrm{i})$ | H |

where $\mathbf{E}, \mathbf{F}, \mathbf{G}$ and $\mathbf{H}$ are constants representing voltage gain, current gain, transconductance and transresistance respectively.

## Non-linear Dependent Sources

Four types of non-linear dependent sources are provided, defined by:

$$
\begin{array}{ll}
\text { Non-linear Voltage Controlled Voltage Source }(\mathrm{v}=\mathrm{f}(\mathrm{v})) & E \\
\text { Non-linear Current Controlled Current Source }(\mathrm{i}=\mathrm{f}(\mathrm{i})) & \mathrm{F} \\
\text { Non-linear Voltage Controlled Current Source }(\mathrm{i}=\mathrm{f}(\mathrm{v})) & \mathrm{G} \\
\text { Non-linear Current Controlled Voltage Source }(\mathrm{v}=\mathrm{f}(\mathrm{i})) & \text { H }
\end{array}
$$

where the function is a polynomial and the arguments multi-dimensional. The polynomial functions are specified by the coefficients $\boldsymbol{p}_{\boldsymbol{0}} \ldots \boldsymbol{p}_{\boldsymbol{n}}$. The significance of the coefficients depends upon the order of the polynomial, as shown below:

## 1st order polynomial

$f_{\boldsymbol{a}}$ is the function argument. The function value $\boldsymbol{f}_{\boldsymbol{v}}$ is computed in the following manner:

$$
f_{v}=P_{0}+\left(P_{1} \cdot f_{a}\right)+\left(P_{2} \cdot f_{a}^{2}\right)+\left(P_{3} \cdot f_{a}^{3}\right)+\left(P_{4} \cdot f_{a}^{4}\right)+\ldots
$$

2nd order polynomial
$f_{a}$ and $f_{b}$ are the function arguments. The function value $f_{v}$ is computed in the following manner:

$$
\begin{gathered}
f_{v}=P_{0}+\left(P_{1} \cdot f_{a}\right)+\left(P_{2} \cdot f_{b}\right)+\left(P_{3} \cdot f_{a}^{2}\right)+\left(P_{4} \cdot f_{a} \cdot f_{b}\right)+\left(P_{5} \cdot f_{b}^{2}\right)+ \\
\left(P_{6} \cdot f_{a}^{3}\right)+\left(P_{7} \cdot f_{a}^{2} \cdot f_{b}\right)+\left(P_{8} \cdot f_{a} \cdot f_{b}^{2}\right)+\ldots
\end{gathered}
$$

## 3rd order polynomial

$f_{a}, f_{b}$ and $f_{c}$ are the function arguments. The function value $f_{v}$ is computed in the following manner:

$$
\begin{aligned}
& f_{v}=P_{0}+\left(P_{1} \cdot f_{a}\right)+\left(P_{2} \cdot f_{b}\right)+\left(P_{3} \cdot f_{c}\right)+\left(P_{4} \cdot f_{a}^{2}\right)+\left(P_{5} \cdot f_{a} \cdot f_{b}\right)+ \\
& \quad\left(P_{6} \cdot f_{a} \cdot f_{c}\right)+\left(P_{7} \cdot f_{b}^{2}\right)+\left(P_{8} \cdot f_{b} \cdot f_{c}\right)+\left(P_{9} \cdot f_{c}^{2}\right)+\left(P_{10} \cdot f_{a}^{3}\right)+\ldots
\end{aligned}
$$

The following pages contain syntax and parameter explanations, together with a number of worked examples, of each of the source options provided by Eldo.

## S, Y, Z Parameter Extraction

A set of commands in Eldo allow the user to extract the $S$ parameters (Scattering parameters), the Y parameters (Admittance) or the Z parameters (Impedance) in the frequency domain for a specified circuit. The circuit can have any number of ports. Special sources must be added at each port of the circuit to be analyzed.

[^5]
## Independent Sources

## Independent Voltage Source

## Independent Source Element

```
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]] [TIME_DEPENDENT_FUNCTION}\mp@subsup{}{}{1}
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val] [LPORT=val]
+ [MODE=keyword] [NOISETEMP=val]
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]] [TIME_DEPENDENT_FUNCTION }\mp@subsup{}{}{1}
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val]
```


## Noise Source

```
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE [THN=VAL] [FLN=VAL]
+ [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL] [FMAX=VAL] [NBF=VAL]
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE [THN=VAL] [FLN=VAL]
+ [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL] [FMAX=VAL] [NBF=VAL]
```


## Tabular Noise Source

```
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC|OCT|IIN|LOG|HARM_DEC|HARM_OCT] [DB|MA]
+ (f1 val1) (f2 val2) ...
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC OOCT |IIN|LOG |HARM_DEC|HARM_OCT] [DB|MA]
+ (f1 val1) (f2 val2) ...
```


## Multi-Tone Source

```
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val]
+ FOUR [DELAY=val] fund1 [fund2 [fund3]] MA |RI|DB|PMA|PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
Vxx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string
+ [IPORT=val] [CPORT=val] [LPORT=val] [MODE=keyword] [NOISETEMP=val]
+ FOUR [DELAY=val] fund1 [fund2 [fund3]] MA|RI|DB|PMA|PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
```

[^6]

## Note

The current flows from the positive node NP , through the voltage source, to the negative node nn.

## Parameters

- xx

Independent voltage source name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- DCVAL

Value of the DC voltage.

- acmag

AC magnitude in volts. Default value is 1 .

- ACPhASE

AC phase in degrees. Default value is zero.

- TIME_DEPENDENT_FUNCTION

Refers to the time dependence of the voltage source (pwl, pulse, exp, pattern, sSFm and SIN). A multi-tone sine wave time dependence can also be defined with the four keyword as detailed in the separate syntax. (See below for more details).

- TC1, тC2

First and Second order temperature coefficients. Default values are zero. тс2 can be specified even if $\mathbf{T C 1}$ is not.

$$
\operatorname{VVAL}(T)=\operatorname{VAL}\left(T_{n o m}\right)\left(1+\mathrm{TC} 1\left(T-T_{n o m}\right)+\mathrm{TC} 2\left(T-T_{n o m}\right)\right)
$$

The above equation defines the value of the voltage (VVAL) as a function of temperature, where $\boldsymbol{T}$ is the operating temperature specified either by the .TEMP command, or the $\boldsymbol{T}$ parameter. Tnom is the nominal temperature for which the voltage source has voltage VAL. Default value of Tnom is $27^{\circ} \mathrm{C}$ and is adjustable using . OPtion tnom.

- noise

Generates a noise source.

## Note

For the Noise Source, at least one parameter has to be specified after the noise keyword, otherwise Eldo issues the following message: "Incorrect number of parameters for noise source VNOISE"

- THN

Defines the white noise level in $\mathrm{A}^{2} / \mathrm{Hz}$ or $\mathrm{V}^{2} / \mathrm{Hz}$ respectively. Can be specified as a biasdependant expression.

- FLN

Defines the $1 / f$ or Flicker Noise level at 1 Hz in $\mathrm{A}^{2} . \mathrm{Hz}^{(1-\mathrm{alpha})}$ or $\mathrm{V}^{2} . \mathrm{Hz}^{(1-\text { alpha) }}$ respectively. Default is 0 . Can be specified as a bias-dependant expression.

- ALPHA

Frequency exponent for 1/f noise.

- FC

Cut-off frequency of the low pass noise filter.

- $\mathbf{N}$

Filter order.

- FMIN

Lower limit of the noise frequency band.

- FMAX

Upper limit of the noise frequency band.
Note
FMIN and FMAX define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency band in the case of filters or oscillators and mixers that exhibit frequency conversion.

- NBF

Specifies the number of sinusoidal sources with randomly distributed amplitude and phase from which the noise source is composed. Default is 50 .

## Note

Parameters fmin, fmax and NBF of Noise Sources are taken into account for Transient analysis only.

Please refer to ".NOISETRAN" on page 747 for further information.

- NOISE TABLE

Keyword indicating that the noise source has a tabular description. See "Noise Table Function" on page 330.

- INTERP

Specifies how to interpolate between different frequency values: LIN means linear interpolation; LOG, ОСт or DEC are all used in the same sense which is logarithmic, octal, or decimal interpolation; HARM_DEC or HARM_OCT specify a logarithmic or octal interpolation around each harmonic of the .SSTNOISE analysis.

- $\mathrm{f} 1, \mathrm{f} 2$

Frequency values in Hertz.

- val1, val2

Values in $\mathrm{V}^{2} / \mathrm{Hz}$.

- FOUR

Keyword specifying that the source is multi-tone.

- DELAY=val

Specifies the time (seconds) that the output is delayed by. This parameter is only effective in .tran. Default value is zero.

- fund1 [fund2 [fund3]]

Parameters to define fundamental frequencies. A source can be defined with up to 3 tones.

- MA $\left.\right|_{\text {RI }} \mid$ DB $\mid$ PMA $\mid$ PDB $\mid$ PDBM

Keyword defining the format (MA—Magnitude Angle, RI-Real Imaginary, DBMagnitude in dB Angle, pma-Power in Watt Angle, pdb-Power in dB Angle, pdbmPower in dBm Angle). Power formats (PMA, PDB and PDBM) are only allowed on port sources (voltage or current sources where IPORt is specified). For multi-tone, the format is used in conjunction with the real_val1, real_val2 specification below. For tabular (only DB|MA), values are couples f1 val1, see above.

- int_val1

Defines the index of the harmonic according to fund1.

- int_val2

Defines the index of the harmonic according to fund2.

- int_val3

Defines the index of the harmonic according to fund3.
The group of 1 to 3 index values define a frequency. For example, for a source with 3 fundamental frequencies, (int_val1, int_val2, int_val3) specifies the frequency:

```
F = int_val1*fund1+int_val2*fund2+int_val3*fund3
```

- real_val1, real_val2

Defines the complex value of the source for the corresponding frequency in the specified format (MA, RI or DB).

- RPORT

Resistance of the port value which defaults to $50 \Omega$ whenever RPORT_TC1, RPORT_TC2 or IPORt is specified. The possibility of having nonoise on this resistance is allowed.

- zPORT_FILE

Specifies the Touchstone file name that contains the complex port impedance.

- nonoise

Used in conjunction with RPORt. Specifies that no noise model will be used for this device when performing noise analysis. Therefore, the port resistance presents no noise contribution to the noise analysis.

- noISE=1

Specifies that a noise model will be used for this device when performing noise analysis. Therefore, the device presents noise contribution to the noise analysis. This has precedence over any nonoise specification on a .MODEL card.

- RPORT_TC1 \& RPORT_TC2

Temperature coefficients of RPORT: they both default to 0 . If RPORT happens to be 0 (in parametric simulations for instance), there will be no $S$ extraction performed.

- iport

This is a strictly positive number that is unique and is used as the port number: this number is used for naming the outputs (for instance, . РLOt AC $S(1,2)$ ). An error message will be issued if two port instances have the same value for IPORT, or if an IPORT is missing (for example maximum IPORT number found in the netlist is 4 , and there is no instance with IPORT 3).

- CPORT

Capacitor placed in series with rport. Defaults to 0 , in which case it behaves like a zero voltage source (i.e. сроrт has no effect).

## - LPORT

Inductor placed in series with rport. Defaults to 0 .

- MODE=SINGLE | COMMON | DIFFERENTIAL

Mixed-mode $S$ parameter selection.
SIngle specifies the port as single ended, it is dedicated to $S$ parameter extraction. Default. common and differential specify that the port is not single ended. Such ports are split into two linked sources that are either common (same amplitude and same phase) or differential (same amplitude but opposite phases). If the S parameters are extracted a "nonsingle ended" port is equally common and differential depending on which display is required. During simulation (DC, AC or TRAN) this port is either common or differential depending on the specified mode keyword.

- NOISETEMP

Corresponds to the temperature value used for the calculation of the NOISE generated by RPORt. The default is the temperature of the circuit, but should be set to 16.85 to comply with IEEE specifications. When this parameter is specified, it overrides the INPUT_TEMP parameter in the . SNF command.

## Examples

```
vplus n12 n13 24
```

Specifies a fixed voltage of 24 V between nodes n 12 and n13.

```
v7 n4 n9 dc 1.2 ac 1.0e-3
```

Specifies a DC voltage of 1.2 V placed between nodes n 4 and n 9 and an AC voltage of 1 mV .

```
v7 n4 n9 ac 1.2 pwl (0 3 5n 0 10n 0)
```

Specifies an AC voltage source of 1.2 V together with a Piece Wise Linear (PWL) voltage source definition placed between nodes n 4 and n 9 .

```
V1 n1 n2 FOUR fund1 MA
+ (0) 5 0
+ (1) 2.5 -90
.param fund1=100meg
```

The above example defines a source having the following time dependence:

```
V1(t) = 5 + 2.5*sin(2*pi*100meg*t)
    V2 n3 n4 FOUR fund1 fund2 DB
    + (0, 0) 0 0
    + (1, 0) 6 -90
    + (0, 1) -6 0
    + (-2, 2) 0 45
    .param fund1=900meg fund2=1.2giga
```

The value of v 2 will be computed as follows:

```
V2 = A + B* sin(2*pi*900e6*t) + C* cos(2*pi*1.2e9)
    +A*}\operatorname{cos}((-2*900e6 + 2*1.2e9)*2*pi*t + PI/4
```

with:
A is computed as 0 dB from 1 V , i.e. A is 1 V
$B$ is 6 dB with reference to 1 V , then it is roughly 2.0 V
c is -3 dB with reference to 1 V , then it is roughly 0.5 V
The PI/4 term at the end of the expression corresponds to 45 degrees, as specified in the SPICE card.

Note
Independent voltage sources defined to have a voltage of 0 V may be removed by Eldo in order to simplify calculations. If you wish to use a voltage source as a current probe, use . Option ammeter to prevent Eldo from removing such voltage sources defined to have a voltage of 0 V . Moreover, currents through components may be measured directly, therefore, the use of voltage sources as current probes is not usually necessary.

The next example specifies a current source of 1 A between nodes 1 and 0 . It has a first order temperature coefficient (TC1) of 1 . The second order temperature coefficient (TC2) will default to 0 .

$$
\text { v1 } 101 \text { tc1=1 }
$$

The next example shows how THN and FLN parameters can be specified as bias-dependant expressions:

```
vx p1 p2 NOISE
+ FLN = 'kf_mod*(pow(abs(i(vx)),af))'
+ THN = '(4*K*(temper + 273))/(abs(v(p1,p2)/i(vx)))'
```


## Independent Current Source

## Independent Source Element

```
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]] [TIME_DEPENDENT_FUNCTION }\mp@subsup{}{}{1}
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val] [LPORT=val]
+ [NOISETEMP=val]
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]] [TIME_DEPENDENT_FUNCTION }\mp@subsup{}{}{1}\mathrm{ ]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val]
```


## Noise Sources

```
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]] [RPORT_TC1=val]
+ [RPORT_TC2=val] [IPORT=val] [CPORT=val] [IPORT=val] [NOISETEMP=val]
+ NOISE [THN=VAL] [FLN=VAL] [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL]
+ [FMAX=VAL] [NBF=VAL]
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [IPORT=val] [CPORT=val]
+ ZPORT_FILE=string [LPORT=val] [MODE=keyword] [NOISETEMP=val]
+ NOISE [THN=VAL] [FLN=VAL] [ALPHA=VAL] [FC=VAL] [N=VAL] [FMIN=VAL]
+ [FMAX=VAL] [NBF=VAL]
```


## Tabular Noise Source

```
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC |OCT|LIN|LOG |HARM_DEC|HARM_OCT] (f1 val1) (f2 val2) ...
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val] NOISE TABLE
+ [[INTERP=]DEC|OCT|IIN|LOG |HARM_DEC|HARM_OCT] (f1 val1) (f2 val2) ...
```


## Multi-Tone Source

```
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] [RPORT=val [NONOISE] [NOISE=1]]
+ [RPORT_TC1=val] [RPORT_TC2=val] [IPORT=val] [CPORT=val]
+ [LPORT=val] [NOISETEMP=val]
+ FOUR [DELAY=val] fund1 [fund2 [fund3]] MA |RI|DB|PMA|PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
Ixx NP NN [[DC] DCVAL] [AC [ACMAG [ACPHASE]]]
+ [TC1=val] [TC2=val] ZPORT_FILE=string [IPORT=val] [CPORT=val]
+ [LPORT=val] [MODE=keyword] [NOISETEMP=val]
+ FOUR [DELAY=val] fund1 [fund2 [fund3]] MA |RI|DB|PMA|PDB|PDBM
+ (int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2
+ {(int_val1 [,int_val2 [,int_val3]]) real_val1 real_val2}
```

[^7]

## Note

The current flows from the positive node NP , through the current source, to the negative node nn.

## Parameters

- xx

Independent current source name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- DCVAL

Value of the DC current source in amperes.

- ACMAg

AC magnitude in amperes. Default value is 1 .

- ACPHASE

AC phase in degrees. Default value is 0 .

- TIME_DEPENDENT_FUNCTION

Refers to the time dependence of the voltage source (pwl, pulse, exp, Pattern, ssfm and sIn). A multi-tone sine wave time dependence can also be defined with the four keyword as detailed in the separate syntax. (See below for more details).

- TC1, тC2

First and Second order temperature coefficients. Default values are zero. тс2 can be specified even if тC1 is not.

$$
\operatorname{IVAL}(T)=V A L\left(T_{\text {nom }}\right)\left(1+\mathrm{TC} 1\left(T-T_{\text {nom }}\right)+\mathrm{TC} 2\left(T-T_{\text {nom }}\right)^{2}\right)
$$

The above equation defines the value of the current (IVAL) as a function of temperature, where $\boldsymbol{T}$ is the operating temperature specified either by the .TEMP command, or the $\boldsymbol{T}$ parameter. Tnom is the nominal temperature for which the current source has current VAL. Default value of Tnom is $27^{\circ} \mathrm{C}$ and is adjustable using . OPtion twom.

- noise

Generates a noise source.

## Note

For the Noise Source, at least one parameter has to be specified after the noise keyword, otherwise Eldo issues the following message: "Incorrect number of parameters for noise source INOISE"

- THN

Defines the white noise level in $\mathrm{A}^{2} / \mathrm{Hz}$ or $\mathrm{V}^{2} / \mathrm{Hz}$ respectively. Can be specified as a biasdependant expression.

- FLn

Defines the $1 / f$ or Flicker Noise level at 1 Hz in $\mathrm{A}^{2} . \mathrm{Hz}^{(1-\mathrm{alpha})}$ or $\mathrm{V}^{2} . \mathrm{Hz}^{(1-\mathrm{alpha})}$ respectively. Default is 0 . Can be specified as a bias-dependant expression.

- alpha

Frequency exponent for 1/f noise.

- FC

Cut-off frequency of the low pass noise filter.

- $\mathbf{N}$

Filter order.

- FMIN

Lower limit of the noise frequency band.

## - fmax

Upper limit of the noise frequency band.
Note
FMIN and FMAX define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency band in the case of filters or oscillators and mixers that exhibit frequency conversion.

## - NBF

Specifies the number of sinusoidal sources with randomly distributed amplitude and phase from which the noise source is composed. Default is 50 .

## Note

Parameters fmin, fmax and nbf of Noise Sources are taken into account for Transient analysis only.

Please refer to ".NOISETRAN" on page 747 for further information.

- NOISE TABLE

Keyword indicating that the noise source has a tabular description. See "Noise Table Function" on page 330.

- FOUR

Keyword specifying that the source is multi-tone.

- DELAY=val

Specifies the time (seconds) that the output is delayed by. This parameter is only effective in .tran. Default value is zero.

- fund1 [fund2 [fund3]]

Parameters to define fundamental frequencies. A source can be defined with up to 3 tones.

- MA|RI|DB|PMA|PDB|PDBM

Keyword defining the format (MA-Magnitude Angle, RI-Real Imaginary, DBMagnitude in dB Angle, pma-Power in Watt Angle, pdb-Power in dB Angle, pdbmPower in dBm Angle). Power formats (PMA, PDB and PDBM) are only allowed on port sources (voltage or current sources where IPORT is specified). The format is used in conjunction with the real_val1, real_val2 specification below.

- int_val1

Defines the index of the harmonic according to fund1.

- int_val2

Defines the index of the harmonic according to fund2.

- int_val3

Defines the index of the harmonic according to fund3.
The group of 1 to 3 index values define a frequency. For example, for a source with 3 fundamental frequencies, (int_val1, int_val2, int_val3) specifies the frequency:

```
F = int_val1*fund1+int_val2*fund2+int_val3*fund3
```

- real_val1, real_val2

Defines the complex value of the source for the corresponding frequency in the specified format (MA, RI or DB).

- RPORT

Resistance of the port value which defaults to $50 \Omega$ whenever RPORT_TC1, RPORt_TC2 or IPORt is specified. The possibility of having nonoise on this resistance is allowed.

- zPORT_file

Specifies the Touchstone file name that contains the complex port impedance.

- nonoise

Used in conjunction with RPORt. Specifies that no noise model will be used for this device when performing noise analysis. Therefore, the port resistance presents no noise contribution to the noise analysis.

- NOISE=1

Specifies that a noise model will be used for this device when performing noise analysis. Therefore, the device presents noise contribution to the noise analysis. This has precedence over any nonoise specification on a .model card.

- RPORT_TC1 \& RPORT_TC2

Temperature coefficients of RPORT: they both default to 0 . If RPORT happens to be 0 (in parametric simulations for instance), there will be no $S$ extraction performed.

## - IPORT

This is a strictly positive number that is unique and is used as the port number: this number is used for naming the outputs (for instance, . PLOT AC $S(1,2)$ ). An error message will be issued if two port instances have the same value for IPORT, or if an IPORT is missing (for example maximum IPORT number found in the netlist is 4 , and there is no instance with IPORT 3).

- CPORT

Capacitor placed in parallel to RPORt. Defaults to 0, in which case it behaves like a zero voltage source (i.e. СРоRт would have no effect).

- LPORT

Inductor placed in series with RPORt. Defaults to 0 .

- MODE=SINGLE $\mid$ COMMON |DIFFERENTIAL

Mixed-mode $S$ parameter selection.
SIngle specifies the port as single ended, it is dedicated to $S$ parameter extraction. Default. common and differential specify that the port is not single ended. Such ports are split into two linked sources that are either common (same amplitude and same phase) or differential (same amplitude but opposite phases). If the S parameters are extracted a "nonsingle ended" port is equally common and differential depending on which display is required. During simulation (DC, AC or TRAN) this port is either common or differential depending on the specified mode keyword.

- NOISETEMP

Corresponds to the temperature value which will be used for the calculation of the NOISE generated by port. The default is the temperature of the circuit, but should be set to 16.85 to comply with IEEE specifications. When this parameter is specified, it overrides the INPUT_TEMP parameter in the .SNF command.

## Examples

$$
\text { i } 23 \text { n } 2 \text { n3 } 1.0 \mathrm{e}-4
$$

Specifies a 0.1 mA current flowing from node n 2 towards node n 3 .

```
i41 n2 n4 dc 1.0e-3 ac 1.0e-6 45
```

Specifies a DC current of 1 mA flowing from node n 2 towards node n 4 and an AC current of $1.0 \times 10^{-6} \mathrm{~A}$ with a phase of 45 degrees.
i1 101 tc1 = 1
Specifies a current source of 1A between nodes 1 and 0 . It has a first order temperature coefficient of 1 . The second order temperature coefficient (TC2) will default to 0 .

The next example shows how thn and fln parameters can be specified as bias-dependant expressions:

```
ix p1 p2 NOISE
+ FLN = 'kf_mod*(pow(abs(i(vx)),af))'
+ THN = '(4*K*(temper + 273))/(abs(v(p1,p2)/i(vx)))'
```


## Amplitude Modulation Function

AM (AMPLITUDE OFFSET FM FC TD)
Generates a time-dependent Amplitude Modulated signal. To be used in combination with independent voltage ( $\mathbf{v x x}$ ) or current ( $\mathrm{I} x \mathrm{x}$ ) sources.

## Parameters

- AMPLITUDE

Signal amplitude. Default is 0 .

- offset

Offset of the signal. Default is 0 .

- FM

Modulation frequency. Default is $1 /$ TSTOP.

- FC

Carrier frequency. Default is 0 .

- TD

Delay before signal starts. Default is 0 .
The waveform is described by:

$$
\begin{aligned}
& V=A M P L I T U D E \times(O F F S E T+\sin (2 \pi \times F M \times(\text { time }-T D))) \\
& \times \sin (2 \pi \times F C \times(\text { time }-T D))
\end{aligned}
$$

## Example

```
vam 1 0 am (10 1 p100 1k 1m)
r1 1 0 1
.tran 1m 20m
.plot tran v(1)
.param p100 = 100
.end
```

The diagram below, has been generated by the above netlist. It shows amplitude modulation for a signal with amplitude 10 and an offset of 1 . There is a signal delay of 1 millisecond and the modulation frequency and carrier frequency is set at 100 and 1000 respectively.

Figure 5-1. AM Function Example


## Exponential Function

EXP (V1 V2 [TD1 [TAU1 [TD2 [TAU2]]]])
Generates an exponentially damped pulse as defined below. To be used in combination with independent voltage ( $\mathrm{v}_{\mathrm{xx}}$ ) or current ( $\mathrm{I}_{\mathrm{xx}}$ ) sources.

## Parameters

- V1

Initial value in volts or amperes.

- V 2

Asymptotic, or target value of the pulse in volts or amperes.

- TD1

Rise delay time in seconds. Default value is zero.

- tau1

Rise time constant in seconds. Default value is tprint.

- TD2

Fall delay time in seconds. Default value is tD1+TPRINT.

- TAU2

Fall time constant in seconds. Default value is tPrint.
The waveform is described by the following relationships:

| Time <br> 0 to TD1 | Voltage |
| :--- | :--- |
| TD1 to TD2 | V 1 |
|  | $\mathrm{~V} 1+(\mathrm{V} 2-\mathrm{V} 1)\left(1-\exp \frac{-(\text { time }-\mathrm{TD} 1)}{\mathrm{TAU} 1}\right)$ |
| TD2 to TSTOP | $\mathrm{V} 1+(\mathrm{V} 2-\mathrm{V} 1)\left(1-\exp \frac{-(\text { time }-\mathrm{TD} 1)}{\mathrm{TAU} 1}\right)+(\mathrm{V} 1-\mathrm{V} 2)\left(1-\exp \frac{-(\text { time }-\mathrm{TD} 2)}{\mathrm{TAU} 2}\right)$ |

Figure 5-2. Exponential Function


## Example

$$
\text { vin n3 } 0 \exp (-4-12 n 10 n 60 n 10 n)
$$

Specifies a voltage source vin between node n 3 and ground. The time dependent voltage is described by:

Time
0 ns to 2 ns
2 ns to 60 ns

60ns - TSTOP

Voltage
-4 V .
Exponential rise from -4 V to -1 V with the rise time constant 10 ns .

Exponential fall from -1 V to -4 V with the fall time constant 10 ns . The tstop value is set in the .tran command.

## Noise Function

NOISE THN FLN ALPHA [FC N] [FMIN] [FMAX] [NBF] [value=\{expr\}]
Generates a noise source and is used in combination with independent voltage ( $\mathrm{v}_{\mathrm{xx}}$ ) or current ( Ixx ) sources.

## Note

This source is effective only during .nOISE and .NOISETRAN analyses. A noise source has no effect during an AC or Transient simulation.

You can define correlation coefficients between two independent noise sources with the command ".NOISE_CORREL" on page 746.

## Parameters

- THN

Defines the white noise level in $\mathrm{A}^{2} / \mathrm{Hz}$ or $\mathrm{V}^{2} / \mathrm{Hz}$ respectively. Default is 0 .

- FLN

Defines the $1 / f$ or Flicker Noise level at 1 Hz in $\mathrm{A}^{2} \cdot \mathrm{~Hz}^{(1-a l p h a)}$ or $\mathrm{V}^{2} \cdot \mathrm{~Hz}^{(1-\text { alpha) })}$ respectively. Default is 0 .

- Alpha

Frequency exponent for $1 / \mathrm{f}$ noise. Default is 1 .

- FC

Cut-off frequency of the low pass noise filter.

- N

Filter order.

- FMIN

Lower limit of the noise frequency band.

- fmax

Upper limit of the noise frequency band.

- nBF

Specifies the number of sinusoidal sources with randomly distributed amplitude and phase from which the noise source is composed. Default is 50 .

- value=\{expr\}

Defines an expression function of (noise) frequency.


## Note

FMIN and FMAX define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency band in the case of filters or oscillators and mixers that exhibit frequency conversion.

The Power Spectral Density (PSD) may be described as:

$$
S_{x}=\left(T H N+\frac{F L N}{f^{A L P H A}}\right)\left(\frac{1}{\left(1+\Omega^{2}\right)^{N}}\right)
$$

where:

$$
\Omega=\frac{f}{F C}
$$

Figure 5-3. Noise Function


## Examples

$$
\text { v1 n1 n2 noise 1e-17 } 01
$$

Specifies a voltage noise source v1 placed between nodes n 1 and n 2 . The White Noise level of the PSD has a value of $1 \times 10^{-17} \mathrm{~V}^{2} / \mathrm{Hz}$, the Flicker Noise level is 0 and the frequency exponent for $1 / f$ noise is 1 .

```
i5 n5 0 noise 1e-20 1e-15 1.3 1meg 2
```

Specifies a current noise source i5 placed between node n 5 and ground. The White Noise level of the PSD has a value of $1 \times 10^{-20} \mathrm{~A}^{2} / \mathrm{Hz}$, the Flicker Noise level is $1 \times 10^{-15}$,the frequency exponent for $1 / \mathrm{f}$ noise is 1.3 , the Cut-off frequency of the low pass filter is 1 MHz and the order of the filter is 2 .

```
.param _pi=3.1415 p_fref=13e6
VN1 VDD 0 5 noise
+ value = { 2*_PI*sin(FREQ/p_fref) }
```

```
.subckt DSQN outp outn ref param: fref=26meg ds_order=3 nscale=1.0
.param p_kds = '2*pi*2*pi/(12*fref)'
.param tom1='2*(ds_order-1)'
Vn outp outn noise
+ value ={nscale * pkds * pwr(2*abs(sin(pi * FREQ / fref)), tom1)}
.ends
```

Defines an expression function of (noise) frequency.

## Noise Table Function

```
NOISE TABLE [ [INTERP=]DEC \(\mid\) OCT \(\mid\) LIN \(\mid\) LOG \(\mid\) HARM_DEC \(\mid\) HARM_OCT] [DB|MA]
\(+(f 1\) val1) (f2 val2) ...
```

Generates a noise source with tabular description and is used in combination with independent voltage ( $\mathbf{v x x}$ ) or current ( $\mathbf{I x x}$ ) sources.

Note
This source is effective only during . noise and . SStnoise analyses. A noise source has no effect during other analysis type simulations, a zero voltage/current source will be assumed.

Specify input noise source values depending on the frequency via the table keyword. Eldo will assume zero current source or zero voltage source in any mode other than noise (for DC, AC, TRAN, and so on).

## Parameters

- NOISE TABLE

Keyword indicating that the noise source has a tabular description.

- INTERP

Specifies how to interpolate between different frequency values: LIN means linear interpolation; LOG, ОСт or DEC are all used in the same sense: logarithmic, octal, or decimal interpolation; HARM_DEC or HARM_OCT specify a logarithmic or octal interpolation around each harmonic of the .SSTNOISE analysis.

- f1, f2

Frequency values in Hz .

- val1, val2

Corresponds to the noise Power Spectral Density of the source at frequency f1, f2 (in $\mathrm{V}^{2} / \mathrm{Hz}$ or $A^{2} / \mathrm{Hz}$ ). Noise is specified relative to the signal.

- MA|DB

Keyword defining the format: MA-Magnitude, DB-Magnitude in dB.

## Examples

```
v1 n1 n2 noise table interp=log
+ 1.0000E+00 'p1*pwr(2*abs(sin(pi* 1.0000E+00 / pref)), 6)'
+ 1.0965E+00 'p1*pwr(2*abs(sin(pi* 1.0965E+00 / pref)), 6)'
+ 1.2023E+00 'p1*pwr(2*abs(sin(pi* 1.2023E+00 / pref)), 6)'
+ 1.3183E+00 'p1*pwr(2*abs(sin(pi* 1.3183E+00 / pref)), 6)'
+ 1.4454E+00 'p1*pwr(2*abs(sin(pi* 1.4454E+00 / pref)), 6)'
+ 1.5849E+00 'p1*pwr(2*abs(sin(pi* 1.5849E+00 / pref)), 6)'
+ 1.7378E+00 'p1*pwr(2*abs(sin(pi* 1.7378E+00 / pref)), 6)'
...
```

Specifies a tabular voltage noise source v1 between nodes n1 and n2, with a logarithmic interpolation around each frequency of the .noise analysis.

## Pattern Function

```
PATTERN VHI VLO TDELAY TRISE TFALL TSAMPLE BITS RB=val R[=val]
PATTERN_FILE=filename
```

Generates a pulsating (digital like) source whose sequential values are defined as a distinct series of 1 and 0 values. To be used in combination with independent voltage ( $\mathrm{v} x \mathrm{x}$ ) or current ( $\mathbf{I x x}$ ) sources. Periodic patterns can also be specified. Parameters of a PATTERN source can be modified with a . STEP command.

A pattern can be written inside an external file and included in the function. It can be described in csv format, SPICE-like format, or blank separator format.

An alternative compact pattern syntax is also available that allows easier user-input of patterns.

## Parameters

- VHI

Voltage representing the 1 string value for pattern sources.

- VLO

Voltage representing the 0 string value for pattern sources.

- TDELAY

Delay before the pattern series is started. The value assigned during this time is the first string value of the series.

- TRISE

Rise time between pattern values in seconds.

- TFALL

Fall time between pattern values in seconds.

- TSAMPLE

Time spent at 1 or 0 pattern value.

- BITS

String of 1,0 and $Z$ values representing a PATTERN source. This can also be specified via a parameter using $\$(P A T)$ where PAT is the parameter as specified in the .PARAM statement. Z means high impedance, and this releases the applied signal, i.e. when the Z state is active, the signal will be disconnected from the node, and the node will be computed by Eldo as if it were a non-input signal.
An alternative compact pattern syntax is also available that allows easier user-input of patterns. The syntax is defined by the following rules:

$$
\begin{aligned}
& \text { BitPattern }=> \\
& {[\text { BitPattern } \wedge \text { number_of_bits }] \mid[\text { BitPattern }] \mid \text { BaseElement BitPattern } \mid \text { BaseElement }} \\
& \text { BaseElement }=>\mathbf{0}|\mathbf{1}| \mathbf{Z}
\end{aligned}
$$

where number_of_bits is a numerical value lower than 100 . You can change this limit using the option "PATTERN_MAX_ALLOWED_COEFF" on page 959.

- $\quad \mathrm{RB}=\mathrm{val}$

Specifies from which bit the pattern is repeated. Used when R is -1 or positive.

- $\quad \mathbf{R}[=v a l]$

Specifies the pattern is periodic.
If $R=-1$, the pattern is repeated continuously (identical to $R$ without any value).
If $\mathrm{R}=0$, the pattern will not be repeated (identical to no R keyword).
If $R=$ a positive value $x$, the pattern is repeated $x$ times.

- PATTERN_FILE=filename

Include a pattern written inside an external file. The pattern file must contain all the information about the pattern and can use parameters defined in the netlist. It can be described in any of the following ways:

- csv format, for example:

```
Amplitude, 0, 100p , 100p, 100p, 10n, 110010101110001100101
```

- SPICE-like format, for example:

```
Amplitude 0
* comment
+ 100p 100p 100p 10n !comment
#com
comment...
...
#endcom
+ $(PPattern)
```

- blank separator format, for example:

```
Amplitude 0 100p 100p 100p 10n $(PPattern)
```

- split among several lines with the bits pattern also split, for example:

```
Amplitude, 0,
100p, 100p, 100p,
10n,
1100
1010
1110
0011
00101
```

Known limitations for pattern file specification:

- There can only be one pattern specified in a file
- Any errors in the pattern file will be reported as if it was in the netlist file

Figure 5-4. Pattern Function


## Examples

```
v3 20 0 pattern 5 0 1u 2u 2u 8u 110010101 R
```

Specifying $R$ at the end of the pattern means that it is periodic. Therefore, the equivalent pattern here is: 110010101110010101110010101110010101110 . . . .
v1 12 pattern $5010 n 5 n 10 n 20 n 001111000$
Specifies a DC voltage source placed between nodes 1 and 2 defined by a string of 1 and 0 values. The voltage representing the 0 string value is 0 V and the voltage level representing the 1 voltage level is 5 V . Rise and fall times of the voltage source are 5 and 10 ns respectively. The voltage source has the following characteristics:

1. Between time 0 and 10 ns , the voltage source remains at 0 V (delay $=10 \mathrm{n}$ ).
2. The voltage source remains at 0 V for $2 \times 20 \mathrm{~ns}(t b i t=20 \mathrm{n})$.
3. The voltage source rises to a 5 V level in $5 \mathrm{~ns}($ trise $=5 \mathrm{n})$.
4. The voltage source remains at 5 V for $4 \times 20 \mathrm{~ns}$.
5. The voltage level falls to 0 V in $10 \mathrm{~ns}(\mathrm{tfall}=10 \mathrm{n})$.
6. The voltage level remains at 0 V for $3 \times 20 \mathrm{~ns}$.
```
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN {amp} {-amp}
+ 100p 100p 100p 10n
+ 01111110011111011111111011111100000
+ 00011111110101010111111110011001111
.PARAM amp=400m
.tran 0 1u
.plot tran v(input_pattern)
.step P(amp) 400m 0 50m
.end
```

The above example shows how to sweep parameters of a PATTERN source function using the .step command.

```
VINP input_pattern 0 PATTERN_FILE=pat.csv DC 0.0 AC 1 0.0
```

The above example shows how to specify a pattern file. The file pat.csv contains a pattern described in csv format.

The following show some examples of valid patterns using the alternative compact syntax, the first two specifications are equivalent:

```
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN 100m 0 0 100p 100p 10n
[[100]^4][1^3][0^3] R
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN 100m 0 0 100p 100p 10n
100100100100111000 R
```

The following two specifications are also equivalent:

```
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN 100m 0 0 2n 140p 5n 00
[[[1^2][0^2]]^4] 1010 [1^3][0^3] 1100101
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN 100m 0 0 2n 140p 5n 00
110011001100110010101110001100101
```

The following shows how to define a bit pattern with the alternative compact syntax, with the number of bits exceeding the defult 100 :

```
.option PATTERN_MAX_ALLOWED_COEFF = 102
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN 100m 0 0 10p 10p 500p
[[[1^101][0^2]^4]] 1010 [1^3] 1100101 R
```

The following shows the alternative compact syntax specified as a parameter:

```
.PARAM PPattern ="0[[[1^2][0^2]]^2]1010[1^3][0^3]1100101"
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN 100m 0 100p 2n 140p 5n
$(PPattern) R
```

The following shows another example of the alternative compact syntax:

```
VINP input_pattern 0 DC 0.0 AC 1 0.0 PATTERN Amplitude 0 0 10p 10p
500p [[ [1 ^ 101] [0 ^ 2] ^ 4 ] ] 1010 [1^3] 1100101 R
```

The following example indicates that the pattern should be repeated for ever from bit number 3 (that is, at $3 n$ ):

```
v1 1 0 pat (1 0 0.0n 0.1n 0.1n 1n b101101 rb=3 r=-1)
```

The following example indicates that the pattern should be repeated twice from bit number 3 (that is, at 3n)

```
v1 1 0 pat (1 0 0.0n 0.1n 0.1n 1n b101101 rb=3 r=2)
```


## Pulse Function

PULSE (V0 V1 [TD [TR [TF [PW [PER]]]]])
Generates a periodic pulse as described below. To be used in combination with independent voltage ( $\mathbf{v x x}$ ) or current ( $\mathbf{I} x \mathrm{x}$ ) sources.

## Parameters

- vo

Initial value of DC voltage or current.

- V1

Pulse magnitude in volts or amperes.

- TD

Delay time in seconds. Default value is zero.

- TR

Rise time in seconds. Default value is TPRINT.

- TF

Fall time in seconds. Default value is tprint.

- PW

Pulse width in seconds. Default value is tstor.

- PER

Pulse period in seconds. Default value is tstop.
Note $\qquad$
$\square$
If the parameters TR and TF are both set to 0 , they are assigned a value of TPRINT, the time interval used for the printing of results of the transient analysis, defined in the .TRAN command.

Figure 5-5. Pulse Function


## Example

```
vp n12 n13 pulse(0 5 5n 1n 1n 10n 35n)
```

Specifies the voltage source vp placed between the node n 12 and n 13 . The voltage source has the following characteristics:

1. 0 V from 0 to $5 \mathrm{~ns}(\mathrm{td}=5 \mathrm{n}, \mathrm{v} 0=0)$.
2. Rise from 0 to 5 V in the time period 5 to $6 \mathrm{~ns}(\mathrm{tr}=1 \mathrm{n}, \mathrm{v} 1=5)$.
3. Remain at 5 V from 6 to $16 \mathrm{~ns}(\mathrm{pw}=10 \mathrm{n})$.
4. Fall from 5 to 0 V in the time period 16 to $17 \mathrm{~ns}(\mathrm{tf}=1 \mathrm{n})$.
5. 0 V from 17 to $35 \mathrm{~ns}(\mathrm{per}=35 \mathrm{n})$.
6. Second cycle starting at 35 ns .

Figure 5-6. Voltage Source Characteristics Volts


## Piece Wise Linear Function

```
PWL (T1 V1 {TN VN} [TD=val] [R=val|PWLPERIOD=val] [SHIFT=val] [R]
+ [SCALE=val] [STRETCH=val])
PWL (FILE=pWl_file [TD=val] [R=val|PWLPERIOD=val] [SHIFT=val] [R]
+ [SCALE=val] [STRETCH=val])
PWL (FILE=pWl_file [COL=val] [ISTEP=val] [ISTART=val] [ISTOP=val]
+ [TD=val] [R=val|PWLPERIOD=val] [SHIFT=val] [SCALE=val] [STRETCH=val]
+ [R])
```

Generates a Piece Wise Linear function using straight lines between specified voltage points until TN is reached. To be used in combination with independent voltage ( $\mathrm{V} x \mathrm{x}^{\mathrm{x}}$ ) or current ( Ixx ) sources.

The second two syntaxes above show how Eldo can read PWL corner points from a file, with the last syntax supporting multi-column files.

Shift=val and $\mathbf{R}=\mathrm{val}$ can be used together in the same PWL statement. The keyword $\mathbf{R}$ alone (without a value specified) can be used in conjunction with SHIFT=val, but must be placed at the end of the statement.

The tn vn pairs can be separated by spaces or commas.

## Note

TD and SHIFT are synonymous.

## Parameters

- $\mathrm{V} 1, \ldots$ VN

Value of the source at time $\boldsymbol{T i}$ in volts or amperes. The source value at intermediate times is provided by linear interpolation. A high-impedance can be specified with the $\mathbf{z}$ keyword.

- T1,... TN

Time in seconds, at which $\boldsymbol{V} \boldsymbol{i}$ is supplied, where $\boldsymbol{T i}<\boldsymbol{T i}+1$.

- TD=VAL

Delay time in seconds. Default value is zero.

## Note

If the rise or fall times are 0 , they are assigned a value of $\operatorname{TPRINT}$, the time interval used for the printing of results of the transient analysis, defined in the .TRAN command.

## - R

Specifies a periodically repetitive signal of period TN . The signal repeats from the beginning.
repeat is the time, in units of seconds, which specifies the start point of the waveform to repeat. This time needs to be less than the greatest time point, tn .

- $\mathbf{R}=\mathrm{VAL}$

Specifies a time value of the repeating function. The period will be equal to the last time value specified in the PWL statement, TN , minus the R value.

- PWLPERIOD=VAL

Alternative to $\mathrm{R}=\mathrm{VAL}$. Specifies the period of the periodic waveform.

- SHIFT=VAL

This acts as if the shift value was added to all time values specified in the PWL card.

- SCALE=VAL

Element scale factor. The value of the element is multiplied by scale, which defaults to 1 .

- Stretch=Val

Time scale factor applied to the waveform. Default value is 1 .

- FILE=pwl_file

Allows Eldo to read PWL corner points from the specified file $p w l \_f i l e$. This is a text file that supplies the time-current (tn in) or time-voltage (tn vn) pairs. Engineering units (for example 9 ns ) are allowed. The time-value pairs are separated by spaces, commas or newline characters. The file can have multiple lines and can have any number of point pairs per line. Continuation signs " + " are not needed.

- COL=VAL

For use with multi-column file specification. Selects the column number of the files. The time values column is the column 0 . So a value less than 1 is not allowed for col.

- IStART=VAL

For use with multi-column file specification. Selects the starting line of data. First data line is 1 .

- ISTOP=VAL

For use with multi-column file specification. Selects the stopping line of data.

- ISTEP=VAL

For use with multi-column file specification. Selects the data interval. A value of nb means Eldo peaks data at each nb lines.

Figure 5-7. Piece Wise Linear Function


## Examples

$$
\text { v1 n3 n4 pwl (4n } 5 \text { 10n } 020 n 030 n 5)
$$

The voltage source v 1 placed between node n 3 and n 4 specifies a signal which is defined by linear interpolation between the values enclosed in the parentheses.

Figure 5-8. Piece Wise Linear Function Example 1


A periodically repetitive signal can be specified as shown in the following example:

```
v1 1 0 pwl (100n 5 150n 1 180n 3 230n 0 300n 5 R)
rl 1 0 1
.tran 1u 2u
.plot tran v(1)
. end
```

The voltage source v1 between nodes 1 and 0 will be interpolated between the specified values of VN at time TN and plotted until the time $2 \mu \mathrm{~s}$ is reached. The repetitive part of the waveform starts at 0 ns and has a period of $\mathrm{TN}=300 \mathrm{~ns}$. This is illustrated in Figure 5-9.

## Figure 5-9. Piece Wise Linear Function Example 2



A high-impedance can be specified in PWL statements as shown in the following example:

```
v1 1 0 PWL (0 0 10n 15 15n Z 25n Z 30n 0)
```

At $15 \mathrm{~ns}, \mathrm{v} 1$ is disconnected which means that the rest of the circuit will impose a value on node 1 , that is, node 1 becomes a node to be solved as any other node in the circuit. At 30 ns , v 1 is connected back.

The example below shows the usage of parameters scale and stretch:

```
v1 1 0 pwl ( 0 0 10n 10 SCALE=2)
*v1 1 0 pwl ( 0 0 10n 10 STRETCH=2)
r1 1 0 1
.tran 1n 10n
.plot tran v(1)
.end
```

When the voltage source with the PWL function is specified with the scale parameter the element is multiplied by a scale factor of 2 along the $y$-axis. When stretch is specified the element is multiplied by a time scale factor along the x -axis.
The example below shows two ways of specifying the file parameter. The name can be specified directly or via a parameter value.

```
v1 1 0 pwl file="stim1.txt" R
.param STIMFILE='"stim.txt"'
v2 2 0 pwl file=$(STIMFILE) R
```

The example below shows a PWL source with multi-column file specification.

```
*test with multicolumn files
*
v1 1 0 dc 0 pwl(file="stim4.txt" col=1 istep=1)
v2 2 0 dc 0 pwl(file="stim4.txt" col=2 istep=2)
r1 1 0 1
r2 2 0 1
.tran 1u 6u
.plot tran v(1) v(2)
.end
```

Contents of stim4.txt file:

```
#time v1 v2
0 1.0 9.0
500e-9 2.0 2.0
1e-6 3.0 13.0
2e-6 4.0 4.0
3e-6 5.0 15.0
4e-6 6.0 6.0
5e-6 7.0 7.0
v1 1 0 pwl file="stim1.txt" R
.param STIMFILE='"stim.txt"'
v2 2 0 pwl file=$(STIMFILE) R
```

The file stim4.txt is a multi-column set of data. This file is structured in a such a way that each line consists of a time value, TN, and source values, VN1, VN2. This example is a three column file. The columns are internally labeled beginning $0(0,1,2)$.

For the first PWL source in the main netlist:

```
v1 1 0 dc 0 pwl(file="stim4.txt" col=1 istep=1)
```

Eldo will parse the source value in column 1 with a step of 1 . It is equivalent to writing:

```
v1 1 0 dc 0 pwl(0 1.0 500ns 2.0 1us 3.0 2us 4 3us 5 4us 6 5us 7)
```

For the second PWL source in the main netlist:

```
v2 2 0 dc 0 pwl(file="stim4.txt" col=2 istep=2)
```

Eldo will parse the source value in column 2 with a step of 2 . It is equivalent to writing:

```
v2 2 0 dc 0 pwl(0 9.0 1us 13.0 3us 15 5us 7)
```

When the voltage source with the PWL function is specified with the scale parameter the element is multiplied by a scale factor of 2 along the $y$-axis. When Stretch is specified the element is multiplied by a time scale factor along the x -axis.

## Single Frequency FM Function

SFFM (SO SA [FC [MDI [FS]]])
Generates a single frequency FM modulated signal. To be used in combination with independent voltage ( vxx ) or current ( $\mathrm{I} x \mathrm{x}$ ) sources.

## Parameters

- so

Offset voltage in volts or current in amperes.

- $\quad$ SA

Magnitude of signal in volts or amperes.

- FC

Carrier frequency in Hertz. Default value is $1 /$ tstop.

- MDI

Modulation index. Default value is zero.

- FS

Signal frequency in Hertz. Default value is $1 /$ tstop.
The shape of the waveform is described by:

$$
\text { value }=S O+S A \times \sin ((2 \pi \times F C \times \text { time })+M D I \times \sin (2 \pi \times F S \times \text { time }))
$$

## Example

$$
\text { v1 n12 } 0 \text { sffm ( } 0 \text { 1 } 20 \mathrm{meg} 2.5 \text { 2meg })
$$

Specifies a voltage source v1 placed between node n12 and ground. The voltage has 0 offset and an amplitude of 1 V . The carrier frequency of 20 MHz is modulated with the signal frequency of 2 MHz , the modulation index being 2.5 .

Figure 5-10. Single Frequency FM Function


## Sine Function

SIN (VO VA [FR [TD [THETA [PHASE]]]])
Generates a sinusoidal or a damped sine wave. To be used in combination with independent voltage ( $\mathbf{v x x}$ ) or current ( $\mathbf{I} x \mathrm{x}$ ) sources.

## Parameters

- vo

Offset voltage in volts or offset current in amperes.

- VA

Sine wave nominal starting amplitude in volts or amperes.

- FR

Frequency in Hertz. Default value is $1 /$ Tstop.

- TD

Delay time in seconds. Default value is zero.

- theta

Damping factor in $1 / \mathrm{sec}$. Default value is zero.

- PHASE

Phase delay in degrees. Default value is zero.
The waveform is described by:
for $t<T D$

$$
V=V O+V A \times \sin \left(2 \pi \times \frac{P H A S E}{360}\right)
$$

for $t \geq T D$

$$
V=V O+V A \times \exp (-(t-T D) \times T H E T A) \times \sin \left(2 \pi \times\left(F R \cdot(t-T D)+\frac{P H A S E}{360}\right)\right)
$$

Figure 5-11. Sine Function


## Examples

$$
\text { vsin n2 n3 } \sin (01105000)
$$

Specifies the voltage source vsin between nodes n 2 and n 3 of amplitude 110 V and frequency 50 Hz .

Figure 5-12. 1st Sine Function Example
Volts


$$
\text { vsin n4 n9 } \sin (05050.05 \text { 9) }
$$

Specifies the voltage source vsin placed between nodes $n 4$ and $n 9$ with an amplitude of 50 V and frequency of 50 Hz . It has a delay of 0.05 s with a decay factor of 9 .

Figure 5-13. 2nd Sine Function Example


## Trapezoidal Pulse With Bit Pattern Function

PBIT V0 V1 TD TD01 TR01 TD10 TF10 BITTIME \{PATTERN\} [R]
Generates a trapezoidal pulse with bit pattern source. This describes a bit pattern as a series of trapezoidal pulses with linear rise and fall waveforms. To be used in combination with independent voltage ( $\mathbf{v x x}$ ) or current ( $\mathrm{I} x \mathrm{x}$ ) sources.

## Parameters

- V0

Voltage (or current) representing the zero bit value.

- V1

Voltage (or current) representing the one bit value.

- TD

Delay before the series is started. The value assigned during this time is the first string value of the series.

- TD01

Time delay for 0-1 bit transition in seconds. Default is 0 .

- TR01

Rise time for 0-1 bit transition in seconds. Default is TSTEP.

- TD10

Time delay for 1-0 bit transition in seconds. Default is 0 .

- TF10

Fall time for 1-0 bit transition in seconds. Default is TSTEP.

- BITTIME

Bit time for complete transition in seconds.

- Pattern

Pattern depicting value at end of each bit time.

- R

Specifying $R$ at the end of the pattern means that it is periodic.

Figure 5-14. Trapezoidal Pulse with Bit Pattern


## Examples

v1 10 pbit $150 n 1 n 0.5 n$ 0n 1n $5 n 101011101000011 R$
Specifies the voltage source, V1 as a trapezoidal voltage pulse source between nodes 1 and 0 . The source has the following characteristics:

The zero bit value is 1 V . The one bit value is 5 V .
There is no delay before the series is started.
Time delay for $0-1$ bit transition is 1 ns .
Rise time for $0-1$ bit transition is 0.5 ns .
Time delay for 1-0 bit transition is 0 ns .
Fall time for 1-0 bit transition is 1 ns .
Bit time for complete transition is 5ns.
The bit pattern has fifteen bits which is repeated until the simulation run ends.

## Exponential Pulse With Bit Pattern Function

EBIT V0 V1 TD TD01 TAU01 TD10 TAU10 BITTIME \{PATTERN\} [R]
Generates an exponential pulse with bit pattern source. This describes a bit pattern as a series of exponential pulses with exponential rise and fall waveforms. To be used in combination with independent voltage ( $\mathbf{v x x}$ ) or current ( $\mathrm{I} x \mathrm{x}$ ) sources.

## Parameters

- V0

Voltage (or current) representing the zero bit value.

- V1

Voltage (or current) representing the one bit value.

- TD

Delay before the series is started. The value assigned during this time is the first string value of the series.

- TD01

Time delay for $0-1$ bit transition in seconds. Default is 0 .

- tau01

Rise time constant for 0-1 bit transition in seconds. Default is TSTEP.

- TD10

Time delay for 1-0 bit transition in seconds. Default is 0 .

- TAU10

Fall time constant for 1-0 bit transition in seconds. Default is TSTEP.

- BITTIME

Bit time for complete transition in seconds.

- Pattern

Pattern depicting value at end of each bit time.

- R

Specifying $R$ at the end of the pattern means that it is periodic.

Figure 5-15. Exponential Pulse with Bit Pattern


## Examples

$$
\text { v1 } 10 \text { ebit } 150 n 1 n 0.5 n \text { 0n 1n } 5 n 101011101000011 \text { R }
$$

Specifies the voltage source, V1 as an exponential voltage pulse source between nodes 1 and 0 . The source has the following characteristics:

The zero bit value is 0 V . The one bit value is 5 V .
There is no delay before the series is started.
Time delay for $0-1$ bit transition is 1 ns .
Rise time constant for $0-1$ bit transition is 0.5 ns .
Time delay for 1-0 bit transition is 0ns.
Fall time constant for $1-0$ bit transition is 1 ns .
Bit time for complete transition is 5ns.
The bit pattern has fifteen bits which is repeated until the simulation run ends.

## Dependent Sources

## Voltage Controlled Voltage Source

## Linear (Voltage Gain Block)

```
Exx NP NN [VCVS] NCP NCN VAL [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
Exx NP NN [VCVS] NCP NCN VALO {VALn} [MIN=VAL] [MAX=VAL]
+ [\mathbf{TC1}=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
```


## Polynomial

Exx NP NN [VCVS] POLY(ND) PCP PCN \{PCP PCN\} PN \{PN\}

+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]


## Piece Wise Linear

Exx NP NN PWL(1) NCP NCN PWL_LIST [DELTA=val]

+ [ $\mathbf{T C 1}=\mathrm{VAL}]$ [ $\mathbf{T C 2}=\mathrm{VAL}]$ [SCALE=VAL] [ABS=VAL]


## Multi-Input Gate

Exx NP NN NAND (ND) |AND (ND) | OR (ND) | NOR(ND) PCP PCN \{PCP PCN\}

+ PWL_LIST [ $\mathbf{T C 1}=V A L]$ [ $\mathbf{T C 2}=V A L] ~[S C A L E=V A L] ~[A B S=V A L]$


## Delay Element

Exx NP NN DELAY NCP NCN [TD=val] [ABS=VAL]

## Arithmetic Expression

Exx NP NN VALUE=\{EXPR\} [MIN=VAL] [MAX=VAL]

+ [ $\mathbf{T C} \mathbf{1}=\mathrm{VAL}] \quad[\mathbf{T C} \mathbf{2}=\mathrm{VAL}] \quad[\mathbf{S C A L E}=\mathrm{VAL}] \quad[\mathbf{A B S}=\mathrm{VAL}]$


## Tabular

Exx NP NN [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL]

+ TABLE EXPR=(XN YN) \{(XN YN) \} [ABS=VAL]


## Integral/Derivative

Exx NP NN INTEGRATION|DERIVATION NCP NCN VAL
$+[\mathbf{M I N}=\mathrm{VAL}]$ [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]

## S-domain

Exx NP NN FNS NCP NCN n0 n1 ... nm, p0 p1 ... pn
Exx NP NN PZ NCP NCN a zr1 zil ... zrm zim, b pri pil ... prn pin

## Frequency Dependent

Exx NP NN FREQ NCP NCN f0 a0 ph0 f1 al ph1... fn an phn

+ [RESTORE_CAUSALITY=0|1]


## Ideal Transformer

```
Exx NP NN TRANS[FORMER] NCP NCN VAL [MIN=VAL] [MAX=VAL]
+ [\mathbf{TC1}=\textrm{VAL}] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
```


## Ideal Op-Amp



## Note

The current flows from the positive node NP, through the current source, to the negative node NN.

## Parameters

- xx

Voltage controlled voltage source name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- NCP

Name of the positive controlling node.

- NCN

Name of the negative controlling node.

- VAL

Voltage gain.
The above parameters can be related by:

$$
V(N P)-V(N N)=V A L \times(V(N C P)-V(N C N))
$$

- VALn

Coefficients of the polynomial function:
VALO is a voltage shift,
VAL1 is the 1st order gain,
VAL2 is the 2nd order gain, and so on

The above parameters can be related by:

$$
\begin{aligned}
& V(N P, N N)=V A L 0+V A L 1 \times V(N C P, N C N)+V A L 2 \times V(N C P, N C N)^{2} \\
& +V A L 3 \times V(N C P, N C N)^{3}+\ldots
\end{aligned}
$$

- $\mathbf{M I N}=$ VAL

Minimum output voltage value. Unit Volts.

- $\mathbf{M A X}=\mathrm{VAL}$

Maximum output voltage value. Unit Volts.

- тC1, тC2

First and Second order temperature coefficients. Default values are zero. The output value is updated with temperature according to the formula:

$$
V A L(T)=V A L(T N O M) \times\left(1+T C 1(T-T N O M)+T C 2(T-T N O M)^{2}\right)
$$

- SCALE=VAL

Element scale factor. The value of the element is multiplied by scale, which defaults to 1 .

- $\mathbf{A B S}=$ val

Can be set to 1 or 0 (default is 0 ). If $\mathbf{A B S}=1$, the output value is the absolute value of the signal.

- POLY

Keyword indicating the source has a non-linear polynomial description.

- ND

Order of the polynomial when pOLY is specified. Number of Inputs when nand, nOR, AND, OR is specified. ND must be greater than or equal to 1 . If ND is not specified it will default to 1 .

- PCP

Name of the positive controlling node producing the voltage difference for the function arguments of the polynomial. Number is equivalent to the order of the polynomial.

- PCN

Name of the negative controlling node producing the voltage difference for the function arguments of the polynomial. Number is equivalent to the order of the polynomial.

- PN

Coefficients of the polynomial.

- NAND, NOR, AND, OR

One of these can be specified in place of the existing keyword poly. If nand or and are used, the lower valued command will be used to compute the output. In the case of nOR or OR, the higher valued command will be used. In such cases of NAND/AND/OR/NOR types, Eldo
expects a list of couple values ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST, the output will be the interpolated value $y$. Commas used as delimiters are optional.

- PWL (1)

When specified, a simple interpolation (straight line between two points) will be performed to evaluate the output. A list of couple values ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST is expected.

- PWL_LIST

Consists of a list of couple values ( $\mathrm{x}, \mathrm{y}$ ); interpolation will be made to extract the value, depending on $(\mathrm{v}(\mathrm{ncp})-\mathrm{v}(\mathrm{ncn}))$. x is the voltage value across the controlling nodes NCP and $N C N$, $y$ is the corresponding output value.

- delta=val

This parameter must be in the range of 0 to 0.5 , and is used to smooth out the output. The smooth-out occurs in the portion of the interval determined by the delta value. If delta is 0 , smooth-out does not occur and strict linear interpolation is performed to compute the output. If delta is set to 0.5 the smooth-out occurs over the whole interval.

- delay

The e element is controlled by the voltage, therefore, the item specified after the delay operator must be the values of the positive and negative control nodes. The output is shifted by a delay value of тD.

- TD=VAL

Delay value. The default value of $\boldsymbol{T D}$ is 0 if left unspecified.

- value

Keyword indicating that the source has a functional description. A set of expressions is specified in Expr.

- TABLE

Keyword indicating that the source has a tabular description. The table itself contains pairs of values. EXPR is evaluated, and its value is used to look up an entry in the table. Linear interpolation is made between entries.

- EXPR

A set of expressions, used to set the source value or an entry look up for a tabular description of the source.
i
Expression formats are described in the Eldo Control Language chapter.

Controlled source expressions may also contain voltages, currents or time. Voltages may be the voltage through a node, for example $\mathbf{v}(6)$, or the voltage across two nodes $\mathbf{v}(5,6)$. Currents must be the current through a voltage source, such as $i(\mathrm{v} 1)$.

EXPR is also able to make use of the operators DDT and IDT. DDT stands for derivative, and IDT for integral. DDT and IDT operators utilize the integration scheme which is used by Eldo for computing the derivative/integral.

Please refer to "Arithmetic Functions" on page 78.

- $\mathrm{XN}, \mathrm{YN}$

Input and corresponding output source values for tabular source definitions.

- INTEGRATION|DERIVATION

Specifies that the voltage drop across NP and NN should be equal to the integral (or derivative) of $\boldsymbol{v}(\mathrm{NCP})-\boldsymbol{v}(\mathrm{NCN})$ multiplied by VAL.

- FNS

Specifies a s-domain function for which the transfer function is:

$$
H=\frac{n 0+n 1 \cdot s \ldots+n_{m} \cdot s^{n}}{p 0+p 1 \cdot s \ldots+p_{m} \cdot s^{n}}
$$

If $\boldsymbol{P} \mathbf{2}$ is 0 and $N C N$ is 0 , this is equivalent to the existing FNS device:

```
FNS NCP NCN n0 n1 ... nm, p0 p1 ... pn
```

- n0 n1 ... nm, p0 p1 ... pn

Polynomial coefficients for the transfer function of $\operatorname{FNS}$.

- PZ

When the poles and zeroes are known, the transfer function is:

$$
H=\frac{a \cdot \Pi((s+(z r i+j \cdot 2 \cdot p i \cdot z i i)) \cdot(s+(z r i-2 \cdot p i \cdot z i i)))}{b \cdot \Pi((s+(p r i+j \cdot 2 \cdot p i \cdot p i i)) \cdot(s+(p r i-2 \cdot p i \cdot p i i)))}
$$

For the numerator, $\boldsymbol{i}$ is from 1 to $m$. For the denominator, $\boldsymbol{i}$ is from 1 to $n$.

## Note

The conjugate appears only if the imaginary part is not 0 .

- a, b

Coefficients for the transfer function of $\mathbf{P z}$.

- pr, pi

Poles of the transfer function. pr is the real part, pi the imaginary part.

- zr, zi

Zeroes of the transfer function. zr is the real part, zi the imaginary part.

- FREQ

Specifies a frequency domain description. Enables a frequency dependent voltage controlled source to be simulated for AC, Transient, and MODSST analyses.

- f0 a0 pho f1 a1 ph1... fn an phn

Coefficients for the frequency domain. fi, ai and phi are the frequency, the amplitude in dB , and the phase in degrees respectively. At each frequency point, Eldo will evaluate the amplitude in dB by making a $\log$ interpolation, and will evaluate the phase by making a linear interpolation.

- RESTORE_CAUSALITY=0|1

Having a purely real impedance that varies with the square root of frequency is not physically realizable. It would be non-causal. Thus when modeling a physical resistance, specifying a variation as the square root of frequency can be interpreted by Eldo as either:

- specifying the module of the impedance (default, or restore_CAUSALIty=0), or
- specifying the real part of the impedance, and Eldo computes the imaginary part
(RESTORE_CAUSALITY=1)
- TRANS [FORMER]

Keyword specifying that an ideal transformer is used. It differs from a linear VCVS source by the equations used:

$$
V(N P)-V(N N)=\frac{V(N C P)-V(N C N)}{V A L}
$$

- OPAMP

Keyword specifying that an ideal operational amplifier is used. This models an ideal amplifier of infinite gain. Note: OPAMP is a keyword here; use Exx outp outn POLY(1) OPAMP 0 gain if OPAMP is actually a pin name and if a regular VCVS of gain 'gain' is required.

## Examples

```
e23 n2 n3 14 0 2.0
```

Specifies that the voltage applied between nodes n 2 and n 3 is twice the potential difference between node 14 and ground.

```
e1 2 0 poly (2) 3 0 5 0 0 1 1 2 2 4.5
```

Specifies a 2nd order non-linear voltage controlled voltage source el between node 2 and ground. The two controlling voltages contributing to the voltage difference for the function arguments $f_{\boldsymbol{a}}$ and $f_{\boldsymbol{b}}$ occur between node 3 (NCP1) and ground (NCN1), and node 5 (NCP2) and
ground (NCN2). Polynomial coefficients are $\mathrm{P} 0=0, \mathrm{P} 1=1, \mathrm{P} 2=1, \mathrm{P} 3=2$ and $\mathrm{P} 4=4.5$. The resultant non-linear voltage function has the following form:

$$
\mathrm{f}_{\mathrm{v}}=\mathrm{f}_{\mathrm{a}}+\mathrm{f}_{\mathrm{b}}+2 \mathrm{f}_{\mathrm{a}}^{2}+4.5 \mathrm{f}_{\mathrm{a}} \mathrm{f}_{\mathrm{b}}
$$

where:
$f_{a}$ is the voltage difference between the controlling nodes NCP1 and NCN1.
$f_{b}$ is the voltage difference between the controlling nodes NCP2 and NCN2.

```
e1 1 2 value = {v(3,4)*i(v5)}
```

Specifies that the voltage applied between nodes 1 and 2 is the instantaneous power calculated by multiplying the voltage across nodes 3 and 4 and the current through V5.

```
V1 A 0 1
r1 A 0 1
V2 B 0 5
r2 B 0 5
E3 3 0 NAND (2) A O B O (-10,-30) (10,30)
r3 3 0 1
```

This example shows the use of the NAND keyword. In this case, the command of lower value is used, i.e. it is $v(A, 0)$ which will be used, the voltage on node 3 will be 3 V (interpolation for x in $[-10,10]$ and $y$ in $[-30,30]$ ).

```
V1 A 0 1
r1 A 0 1
E3 3 0 PWL(1) A O (-10,-30) (10,30)
r3 3 0 1
.DC V1 1 10 1
```

Specifies a voltage controlled voltage source between nodes 3 and 0 . The voltage across $\mathbf{E} 3$ is controlled by the PWL voltage at node A. The . Dc command changes the voltage at node A between 1 V and 10 V . With the VCVS definition, $\mathrm{V}(3)$ changes according to the voltage on A :

$$
\begin{aligned}
& \text { when } V(A)=-10, I(G 3)=-30 \\
& \text { when } V(A)=10, I(G 3)=30
\end{aligned}
$$

then by linear interpolation, we find that:

$$
\begin{aligned}
& \text { when } V(A)=1, I(G 3)=3 \text {, } \\
& \text { when } V(A)=10, I(G 3)=30 .
\end{aligned}
$$

```
*SEARCH MAX must be 3.7276 and min must be 2.2758
E2 2 0 FREQ 1 0
+1k 20 0
+1e10 5 0
v1 1 0 2 ac 1
r1 1 2 1k
r2 2 0 1k
.ac dec 10 1e7 1e9
```

Specifies a voltage controlled voltage source in the frequency domain. It is between nodes 2 and 0 and the voltage across those two pins is equal to the GAIN(f) multiplied by $\mathrm{V}(1,0)$.

## Current Controlled Current Source

## Linear (Current Gain Block)

```
Fxx NP NN [CCCS] VN VAL [MIN=VAL] [MAX=VAL]
+ [\mathbf{TC1}=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
```


## Polynomial

Fxx NP NN [CCCS] POLY(ND) VN \{VN\} PN \{PN\}

+ [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL]
$+[\mathbf{A B S}=\mathrm{VAL}]$


## Piece Wise Linear

Fxx NP NN PWL(1) VN PWL_LIST [DELTA=val]

+ [ $\mathbf{T C} \mathbf{C}=\mathrm{VAL}] \quad[\mathbf{T C 2}=\mathrm{VAL}] \quad$ [SCALE=VAL] [ABS=VAL]


## Multi-Input Gate

Fxx NP NN NAND (ND) |AND (ND) |OR(ND) $\operatorname{NOR(ND)~VN~\{ VN\} ~}$

+ PWL_LIST [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]


## Delay Element

Fxx NP NN DELAY VN [TD=val] [ABS=VAL]

## Integral/Derivative

Fxx NP NN INTEGRATION|DERIVATION VN VAL [MIN=VAL] [MAX=VAL]

+ [ $\mathbf{T C} \mathbf{C}=\mathrm{VAL}] \quad[\mathbf{T C 2}=\mathrm{VAL}] \quad[\mathbf{S C A L E}=\mathrm{VAL}] \quad$ [ $\mathbf{A B S}=\mathrm{VAL}]$


## S-domain

Fxx NP NN FNS VN n0 n1 ... nm, p0 p1 ... pn
Fxx NP NN PZ VN a zr1 zil ... zrm zim, b pr1 pil ... prn pin


## Note

The current flows from the positive node NP, through the current source, to the negative node NN. NCP and NCN are the positive and negative controlling nodes for source vn.

## Parameters

- xx

Current controlled current source name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- VN

Name of the voltage source through which the controlling current flows. The direction of positive controlling current flow is from the positive node, through the source, to the negative node of VN. When poly is specified, one name must be added for each dimension of the polynomial. If poly is not specified, it is assumed that there is only one dimension for which a name should be added.

- val

Current gain.
The above parameters can be related by:

$$
I(F x x)=I(V N A M) \times V A L
$$

- $\quad \mathbf{M I N}=\mathrm{VAL}$

Minimum output current value. Unit Amps.

- $\quad$ MAX=VAL

Maximum output current value. Unit Amps.

- TC1, TC2

First and Second order temperature coefficients. Default values are zero. The output value is updated with temperature according to the formula:

$$
V A L(T)=V A L(T N O M) \times\left(1+T C 1(T-T N O M)+T C 2(T-T N O M)^{2}\right)
$$

- SCALE=VAL

Element scale factor. The value of the element is multiplied by SCALE, which defaults to 1 .

- $\mathbf{A B S}=\mathrm{val}$

Can be set to 1 or 0 (default is 0 ). If $\mathbf{A B S}=1$, the output value is the absolute value of the signal.

- poly

Keyword indicating the source has a non-linear polynomial description.

- ND

Order of the polynomial when pOLY is specified. Number of Inputs when nand, nOR, AND, OR is specified. ND must be greater than or equal to 1 . If ND is not specified it will default to 1 .

- PN

Coefficients of the polynomial.

- NAND, NOR, AND, OR

One of these can be specified in place of the existing keyword poly. If nand or and are used, the lower valued command will be used to compute the output. In the case of nor or OR, the higher valued command will be used. In such cases of NAND/AND/OR/NOR types, Eldo expects a list of device names ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST, the output will be the interpolated value y . Commas used as delimiters are optional.

- PWL (1)

When specified, a simple interpolation (straight line between two points) will be performed to evaluate the output. A list of couple values ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST is expected.

- PWL_LIST

Consists of a list of couple values ( $\mathrm{x}, \mathrm{y}$ ); interpolation will be made to extract the value, depending on $i(v n) . x$ is the current through the controlling node vn, $y$ is the corresponding output value.

- DELTA=VAL

This parameter must be in the range of 0 to 0.5 , and is used to smooth out the output. The smooth-out occurs in the portion of the interval determined by the delta value. If delta is 0 , smooth-out does not occur and strict linear interpolation is performed to compute the output. If delta is set to 0.5 the smooth-out occurs over the whole interval.

- delay

The $\mathbf{F}$ element is controlled by the current, therefore, the item specified after the delay operator must be a device name, vn. The output is shifted by a delay value of TD .

- TD=VAL

Delay value. The default value of TD is 0 if left unspecified.

- INTEGRATION|DERIVATION

Specifies that the current flowing through $\mathbf{F x x}$ should be equal to the integral (or derivative) of $\boldsymbol{i}(\mathrm{VN})$ multiplied by VAL.

## - FNS

Specifies a s-domain function for which the transfer function is:

$$
H=\frac{n 0+n 1 \cdot s \ldots+n_{m} \cdot s^{n}}{p 0+p 1 \cdot s \ldots+p_{m} \cdot s^{n}}
$$

If $\boldsymbol{P} \mathbf{2}$ is 0 and $\boldsymbol{N C N}$ is 0 , this is equivalent to the existing FNS device:

```
FNS NCP NCN n0 n1 ... nm, p0 p1 ... pn
```

- n0 n1 ... nm, p0 p1 ... pn

Polynomial coefficients for the transfer function of FNS.

- PZ

When the poles and zeroes are known, the transfer function is:

$$
H=\frac{a \cdot \Pi((s+(z r i+j \cdot 2 \cdot p i \cdot z i i)) \cdot(s+(z r i-2 \cdot p i \cdot z i i)))}{b \cdot \Pi((s+(p r i+j \cdot 2 \cdot p i \cdot p i i)) \cdot(s+(p r i-2 \cdot p i \cdot p i i)))}
$$

For the numerator, $\boldsymbol{i}$ is from 1 to m . For the denominator, $\boldsymbol{i}$ is from 1 to n .
Note
The conjugate appears only if the imaginary part is not 0 .

- a, b

Coefficients for the transfer function of $\mathbf{P z}$.

- pr, pi

Poles of the transfer function. pr is the real part, pi the imaginary part.

- zr, zi

Zeroes of the transfer function. zr is the real part, zi the imaginary part.

## Examples

$$
\mathbf{f} 7 \mathrm{n} 4 \mathrm{n} 6 \text { v9 } 7
$$

Specifies that the current through f7 flowing from node n 4 to node n 6 is seven times the current of $v 9$.

```
f1 2 0 poly (2) v1 v2 0 1 1 3
```

Specifies a 2nd order non-linear current controlled current source $f 1$ placed between node 2 and ground. The names of the zero voltage sources sensing the current for the function arguments of the polynomial are v1 and v2. Polynomial coefficients are $\mathrm{PN} 0=0, \mathrm{PN} 1=1$ and $\mathrm{PN} 2=3$. The resultant non-linear current function has the following form:

$$
f_{v}=f_{a}+f_{b}+3 f_{a}^{2}
$$

where $f_{\boldsymbol{a}}$ and $f_{\boldsymbol{b}}$ are equal to the current flowing through V1 and V2 respectively.

```
f2 3 0 poly (3) v1 v2 v3 0 1 1 3 2.5
```

Specifies a 3rd order non-linear current controlled current source f2 placed between node 3 and ground. The names of the zero voltage sources sensing the current for the function arguments of the polynomial are v1, v2 and v3. Polynomial coefficients are $\mathrm{PN} 0=0, \mathrm{PN} 1=1, \mathrm{PN} 2=1, \mathrm{PN} 3=3$ and $\mathrm{PN} 4=2.5$.

The resultant non-linear current function has the following form:

$$
f_{v}=f_{a}+f_{b}+3 f_{c}+2.5 f_{a}^{2}
$$

where $f_{\boldsymbol{a}}, f_{\boldsymbol{b}}$ and $f_{\boldsymbol{c}}$ are equal to the current flowing through $\mathrm{V} 1, \mathrm{~V} 2$ and V 3 respectively.

```
V1 A 0 1
r1 A 0 1
V2 B 0 5
r2 B 0 5
F3 3 0 NAND (2) V1 V2 (-10,-30) (10,30)
r3 3 0 1
```

This example shows the use of the nAND keyword. In this case, the command of lower value is used, i.e. it is $v(A, 0)$ which will be used, the voltage on node 3 will be 3 V (interpolation for x in $[-10,10]$ and $y$ in $[-30,30])$.

```
V1 A 0 1
r1 A 0 1
F3 3 0 PWL(1) V1 (-10,-30) (10,30)
r3 3 0 1
.DC V1 1 10 1
```

$\mathrm{V}(3)$ will vary from 3 to 30 when $\mathrm{V}(1)$ varies from 1 to 10 .

## Voltage Controlled Current Source

## Linear (Transconductance Gain Block)

Gxx NP NN [VCR|VCCAP|VCCS] NCP NCN VAL [MIN=VAL] [MAX=VAL]
$+[\mathbf{T C 1}=\mathrm{VAL}] \quad[\mathbf{T C 2}=\mathrm{VAL}] \quad[\mathbf{S C A L E}=\mathrm{VAL}] \quad[\mathbf{A B S}=\mathrm{VAL}]$

## Polynomial

```
Gxx NP NN [VCR|VCCAP|VCCS] POLY(ND) PCP PCN {PCP PCN} PN {PN}
```

$+[\mathbf{M I N}=\mathrm{VAL}]$ [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]

## Piece Wise Linear

Gxx NP NN [VCR|VCCAP|VCCS] [PWL(1)|NPWL (1)|PPWL (1)] NCP NCN PWL_LIST

+ [DELTA=val] [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL]
$+[\mathbf{A B S}=\mathrm{VAL}]$


## Multi-Input Gate

```
Gxx NP NN NAND (ND)|AND (ND)|OR(ND)|NOR(ND) PCP PCN {PCP PCN}
+ PWL_LIST [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
```


## Delay Element

Gxx NP NN DELAY NCP NCN [TD=val] [ABS=VAL]

## Arithmetic Expression

Gxx NP NN VALUE=\{EXPR\} [MIN=VAL] [MAX=VAL]

+ [ $\mathbf{T C} \mathbf{1}=\mathrm{VAL}] \quad[\mathbf{T C} \mathbf{2}=\mathrm{VAL}] \quad[\mathbf{S C A L E}=\mathrm{VAL}] \quad[\mathbf{A B S}=\mathrm{VAL}]$
Tabular
Gxx NP NN [VCR|VCCAP|VCCS] [MIN=VAL] [MAX=VAL] [TC1=VAL] [TC2=VAL]
+ [SCALE=VAL] [ABS=VAL] TABLE EXPR=(XN YN) \{(XN YN) \}


## Integral/Derivative

Gxx NP NN INTEGRATION|DERIVATION NCP NCN VAL $+[\mathbf{M I N}=\mathrm{VAL}]$ [MAX=VAL] [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]

## S-domain

Gxx NP NN FNS NCP NCN n0 n1 ... nm, p0 p1 ... pn
Gxx NP NN PZ NCP NCN a zr1 zil ... zrm zim, b pri pil ... prn pin

## Frequency Dependent

Gxx NP NN FREQ NCP NCN f0 a0 ph0 f1 al ph1... fn an phn

+ [RESTORE_CAUSALITY=0|1]


Note $\qquad$
The current flows from the positive node NP , through the current source, to the negative node Nn .

## Parameters

- $x x$

Voltage controlled current source name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- NCP

Name of the positive controlling node.

- NCN

Name of negative controlling node.

- VAL

Transadmittance in $\Omega^{-1}$.
The above parameters can be related by:

$$
I(G x x)=V A L(V(N C P)-V(N C N))
$$

- MIN=VAL

Minimum output current value. Unit Amps.

- MAX=VAL

Maximum output current value. Unit Amps.

- TC1, TC2

First and Second order temperature coefficients. Default values are zero. The output value is updated with temperature according to the formula:

$$
V A L(T)=V A L(T N O M) \times\left(1+T C 1(T-T N O M)+T C 2(T-T N O M)^{2}\right)
$$

- $\quad$ SCALE $=$ VAL

Element scale factor. The value of the element is multiplied by sCALE, which defaults to 1 .

- ABS=val

Can be set to 1 or 0 (default is 0 ). If $\mathbf{A B S}=1$, the output value is the absolute value of the signal.

- POLY

Keyword indicating the source has a non-linear polynomial description.

- ND

Order of the polynomial when poly is specified. Number of Inputs when NAND, NOR, AND, OR is specified. ND must be greater than or equal to 1 . If ND is not specified it will default to 1 .

- PCP

Name of the positive controlling node giving the voltage difference for the function arguments of the polynomial. Number is equal to the order of the polynomial.

- PCN

Name of the negative controlling node giving the voltage difference for the function arguments of the polynomial. Number is equal to the order of the polynomial.

- PN

Coefficients of the polynomial.

- VCCAP

Used to instantiate a Voltage Controlled CAPacitor. The value of C is computed from the controlling nodes and polynomial coefficients in the same way that the poly voltage control source values are computed.

- VCR

Used to instantiate a Voltage Controlled Resistor. The value of R is computed from the controlling nodes and polynomial coefficients in the same way that the poly voltage control source values are computed. VCR output has an additional formulation, the PWL:

- PWL (1)

When specified, a simple interpolation (straight line between two points) will be performed to evaluate the output. A list of couple values ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST is expected.

- PWL_LIST

Consists of a list of couple values ( $\mathrm{x}, \mathrm{y}$ ); interpolation will be made to extract the value, depending on $(\mathrm{v}(\mathrm{ncp})-\mathrm{v}(\mathrm{ncn}))$. x is the voltage value across the controlling nodes NCP and NCN, y is the corresponding output value.

- NPWL (1)

When specified, the command value used to evaluate the output will be: $\mathrm{V}(\mathrm{ncp})-\mathrm{V}(\mathrm{ncn})$ if $\mathrm{V}(\mathrm{NP})>\mathrm{V}(\mathrm{NN})$, otherwise the command value will be $\mathrm{v}(\mathrm{ncp})-\mathrm{v}(\mathrm{NP})$.

- PPWL (1)

When specified, the command value used to evaluate the output will be: $\mathrm{V}(\mathrm{ncp})-\mathrm{V}(\mathrm{ncn})$ if $\mathrm{V}(\mathrm{NP})<\mathrm{V}(\mathrm{NN})$, otherwise the command value will be $\mathrm{v}(\mathrm{ncp})-\mathrm{v}(\mathrm{NP})$.

## Note

For NPWL(1), node NCN and nN must be the same node.
For pPWL (1), node NCN and NP must be the same node.
Also note that if VCR values are limited to [-1.0e-15 1.0e-15] for instance, then a zero value for VCR is excluded.

- NAND, NOR, AND, OR

One of these can be specified in place of the existing keyword poly. If NAND or and are used, the lower valued command will be used to compute the output. In the case of nor or OR, the higher valued command will be used. In such cases of NAND/AND/OR/NOR types, Eldo expects a list of couple values ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST, the output will be the interpolated value y . Commas used as delimiters are optional.

- delta=val

This parameter must be in the range of 0 to 0.5 , and is used to smooth out the output. The smooth-out occurs in the portion of the interval determined by the delta value. If delta is 0 , smooth-out does not occur and strict linear interpolation is performed to compute the output. If delta is set to 0.5 the smooth-out occurs over the whole interval.

- delay

The g element is controlled by the voltage, therefore, the item specified after the delay operator must be the values of the positive and negative control nodes. The output is shifted by a delay value of $\mathbf{T D}$.

- TD=VAL

Delay value. The default value of $\operatorname{TD}$ is 0 if left unspecified.

## - value

Keyword indicating that the source has a functional description. A set of expressions is specified in EXPR.

- TABLE

Keyword indicating that the source has a tabular description. The table itself contains pairs of values. EXPR is evaluated, and its value is used to look up an entry in the table. Linear interpolation is made between entries.

- EXPR

A set of expressions, used to set the source value or an entry look up for a tabular description of the source.

Expression formats are described in the Eldo Control Language chapter.

Controlled source expressions may also contain voltages, currents or time. Voltages may be the voltage through a node, for example $\mathbf{v}(6)$, or the voltage across two nodes $\mathbf{v}(5,6)$. Currents must be the current through a voltage source, such as $i(\mathrm{v} 1)$.

EXPR is able to make use of the operators DDT and IDT. DDT stands for derivative, and IDT for integral. DDT and IDT operators utilize the integration scheme which is used by Eldo for computing the derivative/integral.

Please refer to "Arithmetic Functions" on page 78.

- $\mathrm{XN}, \mathrm{YN}$

Input and corresponding output source values for tabular source definitions.

- INTEGRATION|DERIVATION

Specifies that the current flowing through Gxx should be equal to the integral (or derivative) of $\boldsymbol{v}(\mathrm{NCP})-\boldsymbol{v}(\mathrm{NCN})$ multiplied by VAL.

- FNS

Specifies a s-domain function for which the transfer function is:

$$
H=\frac{n 0+n 1 \cdot s \ldots+n_{m} \cdot s^{n}}{p 0+p 1 \cdot s \ldots+p_{m} \cdot s^{n}}
$$

If $\boldsymbol{P} \mathbf{2}$ is 0 and $\boldsymbol{N C N}$ is 0 , this is equivalent to the existing FNS device:
FNS NCP NCN n0 n1 ... nm, p0 p1 ... pn

- n0 n1 ... nm, p0 p1 ... pn

Polynomial coefficients for the transfer function of $\operatorname{FNS}$.

- PZ

When the poles and zeroes are known, the transfer function is:

$$
H=\frac{a \cdot \Pi((s-(z r i+j \cdot 2 \cdot p i \cdot z i i)) \cdot(s-(z r i-2 \cdot p i \cdot z i i)))}{b \cdot \Pi((s-(p r i+j \cdot 2 \cdot p i \cdot p i i)) \cdot(s-(p r i-2 \cdot p i \cdot p i i)))}
$$

For the numerator, $\boldsymbol{i}$ is from 1 to m . For the denominator, $\boldsymbol{i}$ is from 1 to $n$.

## Note

The conjugate appears only if the imaginary part is not 0 .

- $a, b$

Coefficients for the transfer function of $\mathbf{P z}$.

- pr, pi

Poles of the transfer function. pr is the real part, pi the imaginary part.

- zr, zi

Zeroes of the transfer function. zr is the real part, zi the imaginary part.

- freq

Specifies a frequency domain description. Enables a frequency dependent voltage controlled source to be simulated for AC, Transient, and MODSST analyses.

- f0 a0 pho f1 a1 ph1... fn an phn

Coefficients for the frequency domain. fi, ai and phi are the frequency, the amplitude in dB , and the phase in degrees respectively. At each frequency point, Eldo will evaluate the amplitude in dB by making a log interpolation, and will evaluate the phase by making a linear interpolation.

- RESTORE_CAUSALITY=0|1

Having a purely real impedance that varies with the square root of frequency is not physically realizable. It would be non-causal. Thus when modeling a physical resistance, specifying a variation as the square root of frequency can be interpreted by Eldo as either:

- specifying the module of the impedance (default, or restore_CAUSALIty=0), or
- specifying the real part of the impedance, and Eldo computes the imaginary part
(RESTORE_CAUSALITY=1)


## Examples

g2 n2 n0 500.0005
Specifies that the current through g2 from node n 2 to ground is equal to 0.0005 times the potential difference between node 5 and ground.

```
g1 3 0 poly (3) 3 0 9 0 5 0 0 1 1 1 3 2 1
```

Specifies a 3rd order non-linear voltage controlled current source g1 placed between node 3 and ground. The three controlling voltages giving the voltage difference for the function arguments occur between node 3 (NCP1) and ground (NCN1), node 9 (NCP2) and ground (NCN2), and node 5 (NCP3) and ground (NCN3). Polynomial coefficients are $\mathrm{P} 0=0, \mathrm{P} 1=1, \mathrm{P} 2=1, \mathrm{P} 3=3$, $\mathrm{P} 4=2$ and $\mathrm{P} 5=1$.

The resultant non-linear voltage function has the following form:

$$
f_{v}=f_{a}+f_{b}+3 f_{c}+2 f_{a}^{2}+f_{a} f_{b}
$$

where:
$\boldsymbol{f}_{\boldsymbol{a}}$ is the voltage difference between the controlling nodes NCP1 and NCN1.
$f_{b}$ is the voltage difference between the controlling nodes NCP2 and NCN2.
$f_{c}$ is the voltage difference between the controlling nodes NCP3 and NCN3.

```
g1 1 2 value={v(6)*v(7)}
```

Specifies current through g1 from node 1 to node 2 to be equal to the product of voltages at nodes 6 and 7.

```
g3 5 0 table v(5)=(0,0) (0.02,2.6e-3) (0.04,4.4e-3)
+(0.06,4.2e-3)(0.08,3.7e-3) (0.10,3.5e-3)(0.12,3.9e-3)
```

Specifies a voltage controlled current source between nodes 5 and 0 . Current out of node 5 is controlled via the table by the voltage at the node 5 . Thus, values in the table describe the I-V device characteristics.

```
V1 A 0 1
r1 A 0 1
V2 B 0 5
r2 B O 5
G3 3 O NAND (2) A O B O (-10,-30) (10,30)
r3 3 0 1
```

This example shows the use of the NAND keyword. In this case, the command of lower value is used, i.e. it is $v(A, 0)$ which will be used, the voltage on node 3 will be 3 V (interpolation for x in $[-10,10]$ and $y$ in $[-30,30]$ ).

```
V1 A 0 1
r1 A 0 1
G3 3 0 PWL(1) A O (-10,-30) (10,30)
r3 3 0 1
.DC V1 1 10 1
```

Specifies a voltage controlled current source between nodes 3 and 0 . The current through G3 is controlled by the PWL voltage at node A. The .DC command changes the voltage at node A between 1 V and 10 V . With the VCCS definition, $\mathrm{V}(3)$ changes according to the voltage on A :

```
when \(V(A)=-10, I(G 3)=-30\)
when \(V(A)=10, I(G 3)=30\)
```

then by linear interpolation, we find that:

$$
\begin{aligned}
& \text { when } V(A)=1, I(G 3)=3 \text {, } \\
& \text { when } V(A)=10, I(G 3)=30 \text {. }
\end{aligned}
$$

## Current Controlled Voltage Source

## Linear (Transresistance Gain Block)

```
Hxx NP NN [CCVS] VN VAL [MIN=VAL] [MAX=VAL]
+ [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]
```


## Polynomial

Hxx NP NN [CCVS] POLY(ND) VN \{VN\} PN \{PN\}
$+[\mathbf{M I N}=\mathrm{VAL}] \quad[\mathbf{M A X}=\mathrm{VAL}] \quad[\mathbf{T C 1}=\mathrm{VAL}] \quad[\mathbf{T C 2}=\mathrm{VAL}] \quad$ [SCALE=VAL] [ABS=VAL]

## Piece Wise Linear

Hxx NP NN PWL(1) VN PWL_LIST [DELTA=val]

+ [ $\mathbf{T C} \mathbf{C}=\mathrm{VAL}] \quad[\mathbf{T C} \mathbf{2}=\mathrm{VAL}] \quad$ [SCALE=VAL] [ABS=VAL]


## Multi-Input Gate

Hxx NP NN NAND (ND) $\operatorname{AND}(N D)|O R(N D)| N O R(N D)$ VN $\{V N\}$

+ PWL_LIST [TC1=VAL] [TC2=VAL] [SCALE=VAL] [ABS=VAL]


## Delay Element

Hxx NP NN DELAY VN [TD=val] [ABS=VAL]

## Integral/Derivation

Hxx NP NN INTEGRATION|DERIVATION VN VAL [MIN=VAL] [MAX=VAL]

+ [ $\mathbf{T C} \mathbf{1}=\mathrm{VAL}] \quad[\mathbf{T C 2}=\mathrm{VAL}] \quad[\mathbf{S C A L E}=\mathrm{VAL}] \quad[\mathbf{A B S}=\mathrm{VAL}]$


## S-domain

Hxx NP NN FNS VN n0 n1 ... nm, p0 p1 ... pn
Hxx NP NN PZ VN a zr1 zil ... zrm zim, b pr1 pil ... prn pin


## Note

The current flows from the positive node NP , through the current source, to the negative node NN. NCP and NCN are the positive and negative controlling nodes for source vn.

## Parameters

## - xx

Current controlled voltage source name.

- NP

Name of the positive node.

- NN

Name of the negative node.

- VN

Name of the voltage source through which the controlling current flows. The direction of positive controlling current flow is from the positive node, through the source, to the negative node of vn. When poly is specified, one name must be added for each dimension of the polynomial. If poly is not specified, it is assumed that there is only one dimension for which a name should be added.

- val

Transresistance in $\Omega$.
The above parameters can be related by:

$$
V(N P)-V(N N)=I(V N A M) \times V A L
$$

- MIN=VAL

Minimum output voltage value. Unit Volts.

- $\quad \mathbf{M A X}=\mathrm{VAL}$

Maximum output voltage value. Unit Volts.

- TC1, TC2

First and Second order temperature coefficients. Default values are zero. The output value is updated with temperature according to the formula:

$$
V A L(T)=V A L(T N O M) \times\left(1+T C 1(T-T N O M)+T C 2(T-T N O M)^{2}\right)
$$

- SCALE=VAL

Element scale factor. The value of the element is multiplied by scale, which defaults to 1 .

- $\mathbf{A B S}=$ val

Can be set to 1 or 0 (default is 0 ). If $\mathbf{A B S}=1$, the output value is the absolute value of the signal.

- POLy

Keyword indicating the source has a non-linear polynomial description.

- ND

Order of the polynomial when poly is specified. Number of Inputs when nand, nor, and, OR is specified. ND must be greater than or equal to 1 . If ND is not specified it will default to 1 .

- PN

Coefficients of the polynomial.

- NAND, NOR, AND, OR

One of these can be specified in place of the existing keyword poly. If nand or and are used, the lower valued command will be used to compute the output. In the case of nor or OR, the higher valued command will be used. In such cases of NAND/AND/OR/NOR types, Eldo expects a list of device names ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST, the output will be the interpolated value y . Commas used as delimiters are optional.

- PWL (1)

When specified, a simple interpolation (straight line between two points) will be performed to evaluate the output. A list of couple values ( $\mathrm{x}, \mathrm{y}$ ) specified as a PWL_LIST is expected.

- PWL_LIST

Consists of a list of couple values ( $\mathrm{x}, \mathrm{y}$ ); interpolation will be made to extract the value, depending on $i(v n) . x$ is the current through the controlling node $\mathrm{VN}, \mathrm{y}$ is the corresponding output value.

- DELTA=VAL

This parameter must be in the range of 0 to 0.5 , and is used to smooth out the output. The smooth-out occurs in the portion of the interval determined by the delta value. If delta is 0 , smooth-out does not occur and strict linear interpolation is performed to compute the output. If delta is set to 0.5 the smooth-out occurs over the whole interval.

- delay

The $\boldsymbol{r}$ element is controlled by the current, therefore, the item specified after the delay operator must be a device name vN. The output is shifted by a delay value of TD.

- TD=VAL

Delay value. The default value of TD is 0 if left unspecified.

- INTEGRATION|DERIVATION

Specifies that the current flowing across NP and NN should be equal to the integral (or derivative) of $\boldsymbol{i}(\mathrm{VN})$ multiplied by VAL.

- FNS

Specifies a s-domain function for which the transfer function is:

$$
H=\frac{n 0+n 1 \cdot s \ldots+n_{m} \cdot s^{n}}{p 0+p 1 \cdot s \ldots+p_{m} \cdot s^{n}}
$$

If $\boldsymbol{P 2}$ is 0 and $\boldsymbol{N C N}$ is 0 , this is equivalent to the existing FNS device:

```
FNS NCP NCN n0 n1 ... nm, p0 p1 ... pn
```

- n0 n1 ... nm, p0 p1 ... pn

Polynomial coefficients for the transfer function of $\operatorname{FNS}$.

- PZ

When the poles and zeroes are known, the transfer function is:

$$
H=\frac{a \cdot \Pi((s+(z r i+j \cdot 2 \cdot p i \cdot z i i)) \cdot(s+(z r i-2 \cdot p i \cdot z i i)))}{b \cdot \Pi((s+(p r i+j \cdot 2 \cdot p i \cdot p i i)) \cdot(s+(p r i-2 \cdot p i \cdot p i i)))}
$$

For the numerator, $\boldsymbol{i}$ is from 1 to m . For the denominator, $\boldsymbol{i}$ is from 1 to n .

## Note

The conjugate appears only if the imaginary part is not 0 .

- $a, b$

Coefficients for the transfer function of $\mathbf{P z}$.

- pr, pi

Poles of the transfer function. pr is the real part, pi the imaginary part.

- zr, zi

Zeroes of the transfer function. zr is the real part, zi the imaginary part.

## Examples

$$
\text { h7 n4 n8 v12 } 7.5
$$

Specifies the voltage applied between nodes n 4 and N 8 to be equal to the current through V12 multiplied by $7.5 \Omega$.

```
h1 2 0 poly(1) v1 1 2 4
```

Specifies a 1st order non-linear current controlled voltage source h1 placed between node 2 and ground. The name of the zero voltage source sensing the current for the function arguments is V 1 . Polynomial coefficients are $\mathrm{P} 0=1, \mathrm{P} 1=2$ and $\mathrm{P} 2=4$.

The resultant non-linear voltage function has the following form:

$$
f_{v}=1+2 f_{a}+4 f_{a}^{2}
$$

where $f_{a}$ is equal to the current flowing through V 1 .
h2 30 poly (3) v1 v2 v3 0111
Specifies a 3rd order non-linear current controlled voltage source H2 placed between node 3 and ground. The names of the zero voltage sources sensing the current for the function
arguments are V1, V2 and V3. Polynomial coefficients are $\mathrm{P} 0=0, \mathrm{P} 1=1, \mathrm{P} 2=1$ and $\mathrm{P} 3=1$. The resultant non-linear current function has the following form:

$$
f_{v}=f_{a}+f_{b}+f_{c}
$$

where $f_{\boldsymbol{a}}, f_{\boldsymbol{b}}$ and $f_{\boldsymbol{c}}$ are equal to the current flowing through $\mathrm{V} 1, \mathrm{~V} 2$ and V 3 respectively.

```
V1 A 0 1
r1 A 0 1
V2 B 0 5
r2 B 0 5
H3 3 O NAND (2) V1 V2 (-10,-30) (10,30)
r3 3 0 1
```

This example shows the use of the nAND keyword. In this case, the command of lower value is used, i.e. it is $v(A, 0)$ which will be used, the voltage on node 3 will be 3 V (interpolation for x in $[-10,10]$ and $y$ in $[-30,30])$.

```
V1 A 0 1
r1 A 0 1
H3 3 0 PWL(1) V1 (-10, -30) (10,30)
r3 3 0 1
.DC V1 1 10 1
```

$\mathrm{V}(3)$ will vary from 3 to 30 when $\mathrm{V}(1)$ varies from 1 to 10 .

## S, Y, Z Parameter Extraction

## S, Y, Z Parameter Extraction

VYy NP NN IPORT=VAL [RPORT=VAL] [CPORT=VAL] [LPORT=VAL] [MODE=KEYWORD]
Vyy NP NN IPORT=VAL ZPORT_FILE=string [CPORT=VAL] [LPORT=VAL]

+ [MODE=KEYWORD]
IYy NP NN IPORT=VAL [RPORT=VAL] [CPORT=VAL] [LPORT=VAL] [MODE=KEYWORD]
IYy NP NN IPORT=VAL ZPORT_FILE=string [CPORT=VAL] [LPORT=VAL]
+ [MODE=KEYWORD]


## Parameters

- yy

Name of the port.

- NP

Name of the positive Node.

- NN

Name of the Negative Node.

- IPORT

This is a strictly positive number that is unique and is used as the port number: this number is used for naming the outputs (for instance, .PLOT AC S(1,2)). An error message will be issued if two port instances have the same value for IPORT, or if an IPORT is missing (for example maximum IPORT number found in the netlist is 4 , and there is no instance with IPORT 3).

## Optional Parameters

- RPORT

Value of the Reference Impedance in Ohms. Default value is $50 \Omega$.

- CPORT

Capacitor placed in series (for V source) or parallel (for I source) with rport. Defaults to 0 , in which case it behaves like a zero voltage source (i.e. CPORT would have no effect).

- LPORT

Inductor placed in series (for V source) or parallel (for I source) with rport. Defaults to 0 .

- ZPORT_FILE

Specifies the Touchstone file name that contains the port source with a complex impedance from which the $S$ parameters will be extracted from.

- MODE=SINGLE | COMMON |DIFFERENTIAL

Mixed-mode $S$ parameter selection.
single specifies the port as single ended, it is dedicated to $S$ parameter extraction. Default. common and differential specify that the port is not single ended. Such ports are split
into two linked sources that are either common (same amplitude and same phase) or differential (same amplitude but opposite phases). During S parameter extraction a "non single ended" port is equally common and differential depending on which display is required. During simulation (DC, AC or TRAN) this port is either common or differential depending on the specified mode keyword.

## Note

Port numbers in $\mathrm{v}_{\mathrm{yy}}$ instances should range from 1 to the total number of ports without discontinuity. The simulation parameters FMIN, FMAX, and Number of frequency points for the analysis are specified with a . AC command.

For further information, please see "Working with S, Y, Z Parameters" on page 1041.

S, Y, Z Parameter Extraction

# Chapter 6 Analog Macromodels 

## Eldo Analog Macromodels

The following analog macromodels are provided in Eldo:

| Comparator (Single Output) | COMP |
| :--- | :--- |
| Comparator (Differential Output) | COMPD |
| Op-amp (Linear) (Single Output) | OPAMP0 |
| Op-amp (Linear) (Differential Output) | OPAMP0D |
| Op-amp (Linear 1-pole) (Single Output) | OPAMP1 |
| Op-amp (Linear 1-pole) (Differential Output) | OPAMP1D |
| Op-amp (Linear 2-pole) (Single Output) | OPAMP2 |
| Op-amp (Linear 2-pole) (Differential Output) | OPAMP2D |
| Delay | DEL |
| Saturating Resistor | SATR |
| Voltage Limiter | SATV |
| Current Limiter | SATI |
| Voltage Controlled Switch | VSWITCH |
| Current Controlled Switch | CSWITCH |
| Ideal Single-Pole Multiple-Throw Switch | IDEAL_SW |
| Triangular to Sine Wave Converter | TRI2SIN |
| Staircase Waveform Generator | STAIRGEN |
| Sawtooth Waveform Generator | SAWGEN |
| Triangular Waveform Generator | TRIGEN |
| Amplitude Modulator | AMM |
| Pulse Amplitude Modulator | PAM |
| Sample and Hold | SA_HO |
| Track and Hold | TR_HO |
| Pulse Width Modulator | PWM |

Voltage Controlled Oscillator
Peak Detector
Level Detector (Single \& Differential Output)
Logarithmic Amplifier
Anti-logarithmic Amplifier
Differentiator
Integrator
Adder, Subtractor, Multiplier and Divider

VCO
PEAK_D
LEV_D
LOGAMP
EXPAMP
DIFF
INTEG
ADD, SUB, MULT, DIV

## General Notes on the Use of FAS Macromodels

For FAS macromodels, i.e. all those using the y prefix, parameters can be declared in a number of ways. These are listed below in order of priority.

## Note

Note 1
In the instantiation line, using the param keyword. The param: command has to be followed by a white space.
Note 2
In a model command line, the syntax is as follows:
.model mname modfas par=val [par=val]
If this syntax is used, a model name must be declared using the model: keyword in the instantiation.
Note 3
If parameters are not explicitly declared, the parameter default values are used.

[^8]
## Comparator

## Single Output

COMPxx INP INN OUT [MNAME] [VHI=VAL1] [VLO=VAL2]

+ [VOFF=VAL3] [VDEF=VAL4] [TCOM=VAL5] [TPD=VAL6]


## Differential Output

COMPDxx INP INN OUTP OUTN [MNAME] [VHI=VAL1] [VLO=VAL2]

+ [VOFF=VAL3] [VDEF=VAL4] [TCOM=VAL5] [TPD=VAL6]
Figure 6-1. Comparator Macromodel


Eldo offers two comparator macromodels, the single output comparator comp and the differential output comparator Compd.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUT

Output node for the single output comparator

- OUTP

Positive output node for the differential output comparator

- OUtN

Negative output node for the differential output comparator

- MNAME

Name of a model described with the model ... Logic command

- vHI=VAL1

Upper voltage level. Default value is 5 V .

- vLO=VAL2

Lower voltage level. Default value is 0 V .

- VOFF=VAL3

Offset input voltage. The voltage on the positive input node is compared with that on the negative added to vorf. Default value is 0 V .

- VDEF=VAL4

Hysteresis voltage in volts. Default is 0 V .

- тСОМ=VAL5

Commutation time. This is the time for the output to switch from vhi to vio or vice versa. Default value is 1 ns .

- TPD=VAL6

Transit time through the comparator. Default value is zero.
The above parameters can be related in the following way:
Table 6-1. Comparator Parameters

| VIN- | Voltage on INN |
| :--- | :--- |
| VIN+ | Voltage on INP |
| VOUT- | Voltage on OUT (OUTN) |
| VOUT+ | Voltage on OUTP |

If $\operatorname{VIN}+(t)>\operatorname{VIN}-(t)+V O F F+V D E F$
and VIN $+(t-1)<\operatorname{VIN}-(t-1)+V O F F+V D E F$
then the output rises.
If $\operatorname{VIN}+(t)<\operatorname{VIN}-(t)+V O F F-V D E F$
and $\operatorname{VIN}+(t-1)>\operatorname{VIN}-(t-1)+V O F F-V D E F$
then the output falls.

## For a differential comparator

VOUT- = (VHI +VLO) - VOUT+

## Examples

```
compd2 vp vn voutp voutn voff=0.9 vdef=0.1
+ vhi=2.5 vlo=-2.5
```

Specifies a differential output comparator compd2 with input nodes vp (+ve), vn (-ve) and output nodes voutp (+ve), voutn (-ve). The upper and lower thresholds of the comparator are +2.5 V and -2.5 V respectively and input offset is 0.9 V . The comparator exhibits a hysteresis of 0.1 V .

```
*.MODEL LOGIC definition
.model compar logic vhi=2.5 vlo=-2.5
comp1 vinp vinn vout compar voff=0.9 vdef=0.1
```

Specifies a single output comparator comp1 of model type compar with input nodes vinp (+ve), vinn (-ve) and output node vout. The comparator input offset voltage and hysteresis are 0.9 V and 0.1 V respectively. The comparator thresholds are $\pm 2.5 \mathrm{~V}$.

## Op-amp (Linear)

## Single Output

YXX OPAMPO [PIN:] INP INN OUT AGND

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Differential Output

```
Yxx OPAMPOD [PIN:] INP INN OUTN OUTP AGND
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-2. Op-amp (Linear) Macromodel



Two general linear operational amplifier macromodels are available, the single output linear gain op-amp OPAMPO, and the differential output linear gain op-amp opampod. Voltage clipping effects can be described using the voltage limiter macromodel (SATv).

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUT

Output node for the single output op-amp

- OUTP

Positive output node for the differential output op-amp

- OUTN

Negative output node for the differential output op-amp

- AGND

Name of the ground node

Table 6-2. Op-amp (Linear) Model Parameters

| Nr. | Name | Default | Units | Definition |
| :---: | :--- | :--- | :--- | :--- |
| 1 | GAIN $^{1}$ | $1.0 \times 10^{5}$ |  | Amplifier gain |
| 2 | RIN | $1.0 \times 10^{7}$ | $\Omega$ | Input resistance |

Table 6-2. Op-amp (Linear) Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 3 | $\mathrm{M}^{2}$ | 1 |  | Device multiplier |

1. Can also be specified in dB .
2. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

1
See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

yopa1 opamp0 n2 n1 n3 0 param: gain=1000 rin=10meg
Specifies a linear gain operational amplifier yopa1 of type opamp0 having input nodes $n 2(+v e)$ and $\mathrm{n} 1(-\mathrm{ve})$ with output node n 3 . Gain and input resistance parameters are declared explicitly in the instantiation.

```
.model tdk modfas gain=2000 rin=20 meg
yopa1 opamp0d n2 n1 n3 n4 0 model: tdk
```

Specifies a differential linear gain operational amplifier yopa1 of type opamp0d with input nodes n 2 (+ve) and n 1 (-ve) and output nodes n 3 (-ve) and n4 (+ve). Gain and input resistance parameters are declared using the .model command.

## Model Equations

Figure 6-3. Op-amp (Linear) Model Characteristics


## General

$$
\begin{aligned}
& I(\text { inp })=\frac{V(i n p, i n n)}{R I N} \\
& I(i n n)=-\frac{V(i n p, i n n)}{R I N}
\end{aligned}
$$

## Single Output

$$
V(\text { out }, \text { agnd })=G A I N \times V(\text { inp }, \text { inn })
$$

Analog Macromodels Op-amp (Linear)

## Differential Output

$$
\begin{aligned}
& V(\text { outn }, \text { agnd })=-\frac{1}{2} G A I N \times V(\text { inp }, \text { inn }) \\
& V(\text { outp }, \text { agnd })=\frac{1}{2} G A I N \times V(\text { inp }, \text { inn })
\end{aligned}
$$

## Op-amp (Linear 1-pole)

## Single Output

YXX OPAMP1 [PIN:] INP INN OUT AGND

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Differential Output

YXX OPAMP1D [PIN:] INP INN OUTN OUTP AGND
$+[$ PARAM: PAR=VAL $\{P A R=V A L\}] \quad$ [MODEL: MNAME]
Figure 6-4. Op-amp (Linear 1-pole) Macromodel


Two operational amplifier macromodels are implemented, namely the single output linear gain one pole op-amp opamp1 and the differential output one pole op-amp OPAMP1D.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUT

Output node for the single op-amp

- OUTP

Positive output node for the differential output op-amp

- outn

Negative output node for the differential output op-amp

- AGND

Name of the ground node

Table 6-3. Op-amp (Linear 1-pole) Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | GAIN $^{1}$ | $1.0 \times 10^{5}$ |  | Open-loop gain |
| 2 | VOFF | 0 | V | Offset voltage |
| 3 | P1 | $1.0 \times 10^{2}$ | Hz | Dominant pole frequency |

Table 6-3. Op-amp (Linear 1-pole) Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 4 | RIN | $1.0 \times 10^{7}$ | $\Omega$ | Input resistance |
| 5 | CMRR $^{12}$ | 0 |  | Common mode rejection ratio |
| 6 | $\mathrm{M}^{3}$ | 1 |  | Device multiplier |

1. Can also be specified in dB .
2. If $C M R R=0$, then $1 / C M R R$ is ignored in the model equations.
3. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
yopa1 opamp1 n2 n1 n3 0 param: voff=100e-6
```

Specifies a linear gain operational amplifier yopa1 of model type opamp1 having input nodes n 2 (+ve) and n1 (-ve) with output node n3. The op-amp offset voltage is declared explicitly in the instantiation line.

```
.model tdk modfas voff=100e-6
yopa1 opamp1d n1 n2 n3 n4 0 model: tdk
```

Specifies a differential linear gain operational amplifier yopa1 of type opamp1d with input nodes n 1 (+ve) and n2 (-ve) and output nodes n3 (-ve) and n4 (+ve). The offset voltage parameter is declared using the .model command.

## Model Equations

Figure 6-5. Op-amp (Linear 1-pole) Model Characteristics


## General

$$
\begin{aligned}
& I(\text { inp })=\frac{V(i n p, i n n)+V O F F}{R I N} \\
& I(\text { inn })=-\frac{V(\text { inp,inn })+V O F F}{R I N} \\
& T A U=\frac{1}{(2 \pi \times \mathrm{P} 1)} \\
& V A=G A I N \times\left((V(\text { inp }, \text { inn })+V O F F)+\frac{1}{C M R R} \times \frac{(V(\text { inp })+V(\text { inn }))}{2}\right)
\end{aligned}
$$

Note
If $C M R R=0$, then $1 / C M R R$ is ignored. $V A$ is then calculated as if no value for $C M R R$ had been specified.

## Single Output

$$
\frac{V(\text { out }, \text { agnd })}{V A}=\frac{1}{1+T A U \times p}
$$

$\boldsymbol{p}$ is the complex frequency.

## Differential Output

$$
\begin{aligned}
& \frac{V(\text { outn, agnd })}{V A}=-\frac{1}{2}\left(\frac{1}{1+T A U \times p}\right) \\
& \frac{V(\text { outp }, \text { agnd })}{V A}=\frac{1}{2}\left(\frac{1}{1+T A U \times p}\right)
\end{aligned}
$$

## Application Area

A typical application area for the linear one-pole op-amp is in the modeling of two-stage amplifiers including real saturation effects. This application is achieved in three parts as explained below:

1. The first stage of the amplifier is described using the OPAMP1 macromodel with the equation:

$$
\frac{V_{\text {out }}}{V_{\text {in }}}=\frac{G A I N}{(1+T \times p)}
$$

2. Clipping of the voltage is achieved using the voltage limiter macromodel SATV at the output of the OPAMP1 macromodel.
3. The second stage of the amplifier is described using an external capacitor CL, together with a non-linear resistor $R$, implemented as a saturating resistor (SATR macromodel).

Figure 6-6. Op-amp (Linear 1-pole) Application Area


The dominant pole of the amplifier is determined by the following equation:

$$
\mathrm{T} 1=\frac{1}{(2 \pi \times \mathrm{P} 1)}+R \times C L
$$

The non-dominant pole of the amplifier is determined by the following equation:

$$
\mathrm{T} 2=\frac{1}{(2 \pi \times \mathrm{P} 1)} \times(R \times C L)
$$

Figure 6-7. Op-amp (Linear 1-pole) Frequency Response


An example of the above application can be found in "Examples" on page 1459.

## Op-amp (Linear 2-pole)

## Single Output

YXX OPAMP2 [PIN:] INP INN OUT AGND

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Differential Output

```
YXX OPAMP2D [PIN:] INP INN OUTN OUTP AGND
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-8. Op-amp (Linear 2-pole) Macromodel


Two linear 2-pole op-amp macromodels are provided, a single output linear gain two pole opamp OPAMP2, and a differential output two pole op-amp OPAMP2D.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUT

Output node for the single op-amp

- OUTP

Positive output node for the differential output op-amp

- OUTN

Negative output node for the differential output op-amp

- AGND

Name of the ground node

Table 6-4. Op-amp (Linear 2-pole) Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | GAIN $^{1}$ | $1.0 \times 10^{5}$ |  | Open-loop gain |
| 2 | VOFF | 0 | V | Offset voltage |
| 3 | P1 | $1.0 \times 10^{2}$ | Hz | Dominant pole frequency |

Table 6-4. Op-amp (Linear 2-pole) Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 4 | P2 | $1.0 \times 10^{6}$ | Hz | Non-dominant pole frequency |
| 5 | RIN | $1.0 \times 10^{7}$ | $\Omega$ | Input resistance |
| 6 | CMRR $^{12}$ | 0 |  | Common mode rejection ratio |
| 7 | $\mathrm{M}^{3}$ | 1 |  | Device multiplier |

1. Can also be specified in dB .
2. If $C M R R=0$, then $1 / C M R R$ is ignored in the model equations.
3. OPTION YMFACT must be specified for M to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
yopa1 opamp2 pin: n2 n1 n3 0 param: p1=300
```

Specifies a linear two-pole operational amplifier yopa1 of model type opamp2 having input nodes $\mathrm{n} 2(+\mathrm{ve})$ and $\mathrm{n} 1(-\mathrm{ve})$ with output node n 3 . The op-amp dominant pole frequency parameter is declared explicitly in the instantiation line.

```
.model tdk modfas p1=300
yopa4 opamp2d n1 n2 n3 n4 0 model: tdk
```

Specifies a differential linear gain op-amp yopa4 of type opamp2d with input nodes n1 (+ve) and $\mathrm{n} 2(-\mathrm{ve})$ and output nodes $\mathrm{n} 3(-\mathrm{ve})$ and $\mathrm{n} 4(+\mathrm{ve})$. The dominant pole frequency parameter is declared using the .model command.

## Model Equations

Figure 6-9. Op-amp (Linear 2-pole) Model Characteristic


## General

$$
\begin{aligned}
& I(\text { inp })=\frac{V(\text { inp, inn })+V O F F}{R I N} \\
& I(\text { inn })=-\frac{V(\text { inp }, \text { inn })+V O F F}{R I N} \\
& \text { TAU1 }=\frac{1}{(2 \pi \times \mathrm{P} 1)}+\frac{1}{(2 \pi \times \mathrm{P} 2)} \\
& \text { TAU2 }=\frac{1}{(2 \pi \times \mathrm{P} 1)} \times \frac{1}{(2 \pi \times \mathrm{P} 2)} \\
& V A=G A I N \times\left((V(\text { inp }, \text { inn })+V O F F)+\frac{1}{C M R R} \times \frac{(V(\text { inp })+V(\text { inn }))}{2}\right)
\end{aligned}
$$

Note
If $C M R R=0$, then $1 / C M R R$ is ignored. $V A$ is then calculated as if no value for $C M R R$ had been specified.

## Single output

$$
\frac{V(\text { out }, \text { agnd })}{V A}=\frac{1}{1+\mathrm{TAU} 1 \times p+\mathrm{TAU} 2 \times p^{2}}
$$

$\boldsymbol{p}$ is the complex frequency

## Differential output

$$
\begin{aligned}
& \frac{V(\text { outn }, \text { agnd })}{V A}=-\frac{1}{2}\left(\frac{1}{1+\mathrm{TAU} 1 \times p+\mathrm{TAU} 2 \times p^{2}}\right) \\
& \frac{V(\text { outp }, \text { agnd })}{V A}=\frac{1}{2}\left(\frac{1}{1+\mathrm{TAU} 1 \times p+\mathrm{TAU} 2 \times p^{2}}\right)
\end{aligned}
$$

## Delay

DELxx IN OUT VAL
Figure 6-10. Delay Macromodel
Nロー Delay

This macromodel describes an ideal delay element that transfers its input voltage to its output after a specified time delay, where the reference node is ground. The input impedance is infinite.

## Model Pins

- IN

Name of the input node

- out

Name of the output node

## Parameters

- val

Value of the delay in seconds. Must not be greater than hmin.

## Example

del1 a1 a2 2.0e-9
Specifies a delay element placed between nodes a1 and a2, with a delay of 2 ns .

## Note



This macromodel can not be used in a .AC analysis.

## Saturating Resistor

Yxx SATR [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-11. Saturating Resistor Macromodel


An analog saturating resistor macromodel. Current clipping can be specified directly using the parameter Imax. This model is also designed to be used in conjunction with the one- and twopole op-amp macromodels (OPAMP1, OPAMP2) and the voltage limiter SATV. If this option is used, the saturating current is specified indirectly by the value of the dominant pole frequency P1 and the Slew Rate sR.

## Model Pins

- IN

Name of the input node

- OUT

Name of the output node

Table 6-5. Saturating Resistor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | R | 1 | $\Omega$ | Resistance |
| 2 | IMAX | 1 | A | Maximum current |
| 3 | SR | 0 | $\mathrm{~V} / \mu \mathrm{s}$ | Slew rate |
| 4 | P 1 | $1.0 \times 10^{6}$ | Hz | Dominant pole frequency |
| 5 | R 1 | 30 | $\Omega$ | Resistance of 1st order low pass filter |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Example

```
ycl1 satr n1 n2
```

Specifies a current limiter ycl1 of type satr having input node n 1 with output node n2. Default model parameters are used.

## Model Equations

Figure 6-12. Saturating Resistor Model Characteristics


$$
I=\frac{V(\text { in })-V(\text { out })}{R}
$$

If $\boldsymbol{S R}$ is specified

$$
I M A X=\frac{S R}{(2 \pi \times \mathrm{P} 1 \times \mathrm{R} 1)}
$$

## Voltage Limiter

```
Yxx SATV [PIN:] INP INN OUTP OUTN
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-13. Voltage Limiter Macromodel


An analog voltage limiter macromodel, where the input voltage is limited to specified values. The voltage describes exponential behavior in the saturation regions and a 3rd degree polynomial in the working region.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

Table 6-6. Voltage Limiter Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | VMAX | 5 | V | Maximum output voltage |
| 2 | VMIN | -5 | V | Minimum output voltage |
| 3 | VSATP | 4.75 | V | Positive saturation input voltage |
| 4 | VSATN | -4.75 | V | Negative saturation input voltage |
| 5 | NSLOPE | 0.25 |  | Slope of Transfer Function at vSATN |
| 6 | PSLOPE | 0.25 |  | Slope of Transfer Function at vSATP |
| 7 | M $^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.
i
See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
ysat1 satv n2 n1 n3 0 param: vmin=-3.0
```

Specifies a voltage limiter ysat1 of type satv with input nodes n 2 (+ve) and $\mathrm{n} 1(-\mathrm{ve})$ and output nodes n 3 (+ve) and ground ( -ve ). The voltage below which negative saturation occurs is declared explicitly in the instantiation line.

```
.model satur modfas vmax=3.5
ys2 satv n1 n2 n3 0 model: satur
```

Specifies a voltage limiter ys2 of type satv having input nodes n 1 (+ve) and n 2 (-ve) with output nodes n 3 (+ve) and ground (-ve). The voltage above which positive saturation occurs is declared in the .model command.

## Model Equations

Figure 6-14. Voltage Limiter Model Characteristics


For $V($ inp, inn $)>V S A T P \Rightarrow$ positive saturation.
For $V($ inp, inn $)<V S A T N \Rightarrow$ negative saturation.

## Current Limiter

Yxx SATI [PIN:] IN OUT

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

Figure 6-15. Current Limiter Macromodel


An analog current limiter macromodel, where the input current is limited to specified values. The current describes exponential behavior in the saturation regions and a 3rd degree polynomial in the working region.

## Model Pins

- IN

Name of the input node

- OUT

Name of the output node

Table 6-7. Current Limiter Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | IMAX | 5 | A | Maximum output current |
| 2 | IMIN | -5 | A | Minimum output current |
| 3 | ISATP | 4.75 | A | Positive saturation input current |
| 4 | ISATN | -4.75 | A | Negative saturation input current |
| 5 | NSLOPE | 0.25 |  | Slope of Transfer Function at ISATN |
| 6 | PSLOPE | 0.25 |  | Slope of Transfer Function at ISATP |
| 7 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

(i)
See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
ysat1 sati n1 n2 param: imin=-3.0
```

Specifies a current limiter ysat1 of type sati with input node n1 and output node n2. The current below which negative saturation occurs is declared explicitly in the instantiation line.

```
.model satur modfas imax=3.5
ys2 sati n1 n2 model: satur
```

Specifies a current limiter ys2 of type sati having input node n 1 and output node n 2 . The current above which positive saturation occurs is declared in the .MODEL command.

## Model Equations

Figure 6-16. Current Limiter Model Characteristics


For $I($ inp, inn $)>I S A T P \Rightarrow$ positive saturation.
For $I($ inp,$i n n)<I S A T N \Rightarrow$ negative saturation.

## Voltage Controlled Switch

Yxx VSWITCH [PIN:] NP NN CP CN [PARAM: PAR=VAL \{PAR=VAL\}] MODEL: MNAME
Figure 6-17. Voltage Controlled Switch Macromodel


The voltage controlled switch macromodel can be thought of as a voltage controlled resistance, which varies continuously between the 'ON' and 'OFF' resistances defined by the model parameters ron and roff. The resistance change can be defined to be linear or exponential using the level parameter.

Recommendations for switch resistance values:

- Choose a reasonable ratio for $\mathrm{ROFF} / \mathrm{RON}$. A ratio smaller than $1 \times 10^{12}$ ( $1 / \mathrm{GmIN}$ ) is recommended.
- Make ron larger than gmin. $1 \Omega$ is a realistic value.
- Set roff as high as permissible with respect to the ratio and other circuit elements.


## Model Pins

- NP

Name of the input node

- NN

Name of the output node

- CP

Name of the positive controlling node

- CN

Name of the negative controlling node

Table 6-8. Voltage Controlled Switch Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | LEVEL | 1 |  | Model level <br> LEVEL=1—Linear interpolation <br> LEVEL=2—Exponential interpolation <br> LEVEL=3—Hysteresis behavior |
| 2 | VON | 0.95 | V | Control voltage for 'ON' state |

Table 6-8. Voltage Controlled Switch Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 3 | VOFF | 0.05 | V | Control voltage for 'OFF' state |
| 4 | RON | $1.0 \times 10^{-2}$ | $\Omega$ | 'ON' resistance |
| 5 | ROFF | $1.0 \times 10^{10}$ | $\Omega$ | 'OFF' resistance |
| 6 | HYSTERESIS | 0 | V | Switching Hysteresis |
| 7 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

Note


In AC mode, the switch resistance value is equal to that computed in the DC analysis.

## Example

```
ysw1 vswitch n1 n4 n2 n3
```

Specifies a voltage controlled switch ysw1 of type vswitch having input and output nodes n1 and n 4 respectively with a positive controlling node n 2 and negative controlling node n 3 .

## Model Equations

$$
\begin{aligned}
V C T R L & =V(c p)-V(c n) \\
\mathrm{RC} 1 & =\ln \sqrt{R O N \times R O F F} \\
\mathrm{RC} 2 & =\ln \left(\frac{R O N}{R O F F}\right) \\
\mathrm{VC} 1 & =\frac{(V O N+V O F F)}{2} \\
\mathrm{VC} 2 & =V O F F-V O N
\end{aligned}
$$

When $V O N \geq V O F F$
$V C T R L \geq V O N \Rightarrow R S=R O N$
$V C T R L \leq V O F F \Rightarrow R S=R O F F$ where $\boldsymbol{R S}$ is the switch resistance.
$V O F F<V C T R L<V O N$

For LEVEL=1

$$
R S=\frac{R O F F-R O N}{V O F F-V O N} \times V C T R L+\frac{R O N \times V O F F-(R O F F \times V O N)}{V O F F-V O N}
$$

For LEVEL=2

$$
R S=\exp \left(\mathrm{RC} 1-\left(\frac{3 \times \mathrm{RC} 2 \times(V C T R L-\mathrm{VC} 1)}{2 \times \mathrm{VC} 2}\right)+2 \times \frac{\mathrm{RC} 2(V C T R L-\mathrm{VC} 1)^{3}}{(\mathrm{VC} 2)^{3}}\right)
$$

When $V O N<V O F F$

$$
\begin{aligned}
& V C T R L \leq V O N \Rightarrow R S=R O N \\
& V C T R L \geq V O F F \Rightarrow R S=R O F F \\
& V O F F>V C T R L>V O N
\end{aligned}
$$

For LEVEL=3
$V C T R L \leq V O N \Rightarrow R S=R O N$
$V C T R L \geq V O F F \Rightarrow R S=R O F F$
$R S=$
1
$\frac{1}{R O F F}+\frac{\left(\frac{1}{R O F F}-\frac{1}{R O N}\right) \times\left(2(V C-V O F F)^{3}-3\left(V O N \_H Y S-V O F F \_H Y S\right) \times\left(V C-V O F F \_H Y S\right)^{2}\right)}{\left(V O N \_H Y S ~-~ V O F F \_H Y S\right)^{3}}$
for $V O F F>V C T R L>V O N$
where:
VOFF_HYS = VOFF + HYSTERESIS $\times$ HYSTERESIS_STATE
$V O N \_H Y S=V O N+H Y S T E R E S I S \times$ HYSTERESIS_STATE
HYSTERESIS_STATE $=1$, if $V C$ waveform is rising and $V C<V O F F \_H Y S$
HYSTERESIS_STATE $=-1$, if $V C$ waveform is falling and $V C>V O N_{-} H Y S$
HYSTERESIS_STATE = 1 initially

## Current Controlled Switch

Yxx CSWITCH [PIN:] NP NN IC: VNAME<br>+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]

Figure 6-18. Current Controlled Switch Macromodel


The current controlled switch macromodel can be thought of as a current controlled resistance, where the resistance varies continuously between the 'ON' and 'OFF' resistances defined in the model parameters ron and roff. The resistance change can be defined to be linear or exponential using the level parameter.

Recommendations for switch resistance values:

- Choose a reasonable ratio for $\mathrm{ROFF} / \mathrm{RON}$. A ratio smaller than $1 \times 10^{12}$ ( $1 / \mathrm{GmIN}$ ) is recommended.
- Make ron larger than gmin. $1 \Omega$ is a realistic value.
- Set Roff as high as permissible with respect to the ratio and other circuit elements.


## Model Pins

- NP

Name of the input node

- NN

Name of the output node

- VNAME

Controlling current through voltage source

Table 6-9. Current Controlled Switch Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | LEVEL | 1 |  | Model level <br> LEVEL=1—Linear interpolation <br> LEVEL=2—Exponential interpolation |
| 2 | ION | 0.95 | A | Control current for 'ON' state |
| 3 | IOFF | 0.05 | A | Control current for 'OFF' state |
| 4 | RON | $1.0 \times 10^{-2}$ | $\Omega$ | 'ON' resistance |
| 5 | ROFF | $1.0 \times 10^{10}$ | $\Omega$ | 'OFF' resistance |

Table 6-9. Current Controlled Switch Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

Note
In AC mode, the switch resistance value is equal to that computed in the DC analysis.

## Example

```
ysw1 cswitch n1 n2 ic: v1
```

Specifies a current controlled switch ysw1 of type cswitch having input and output nodes n1 and n 2 respectively. The switch is controlled by the current through the voltage source v 1 .

## Model Equations

$$
\begin{aligned}
I C T R L & =I(\text { vname }) \\
\mathrm{RC} 1 & =\ln \sqrt{R O N \times R O F F} \\
\mathrm{RC} 2 & =\ln \left(\frac{R O N}{R O F F}\right) \\
\mathrm{IC} 1 & =\frac{(I O N+I O F F)}{2} \\
\mathrm{IC} 2 & =I O F F-I O N
\end{aligned}
$$

When $I O N \geq I O F F$
$I C T R L \geq I O N \Rightarrow R S=R O N$
$I C T R L \leq I O F F \Rightarrow R S=R O F F$ where $\boldsymbol{R} \boldsymbol{S}$ is the switch resistance.
$I O F F<I C T R L<I O N$
For LEVEL=1

$$
R S=\frac{R O F F-R O N}{I O F F-I O N} \times I C T R L+\frac{R O N \times I O F F-(R O F F \times I O N)}{I O F F-I O N}
$$

For LEVEL=2

$$
R S=\exp \left(\mathrm{RC} 1-\left(\frac{3 \times \mathrm{RC} 2 \times(I C T R L-\mathrm{IC} 1)}{2 \times I \mathrm{C} 2}\right)+2 \times \frac{\mathrm{RC} 2(I C T R L-\mathrm{IC} 1)^{3}}{(I C 2)^{3}}\right)
$$

When ION $<I O F F$

$$
\begin{aligned}
& I C T R L \leq I O N \Rightarrow R S=R O N \\
& I C T R L \geq I O F F \Rightarrow R S=R O F F \\
& I O F F>I C T R L>I O N
\end{aligned}
$$

## For LEVEL=1

$$
R S=\frac{R O F F-R O N}{I O F F-I O N} \times I C T R L+\frac{R O N \times I O F F-(R O F F \times I O N)}{I O F F-I O N}
$$

For LEVEL=2

$$
R S=\exp \left(\mathrm{RC} 1-\left(\frac{3 \times \mathrm{RC} 2 \times(I C T R L-I \mathrm{C} 1)}{2 \times I \mathrm{C} 2}\right)+2 \times \frac{\mathrm{RC} 2(I C T R L-I \mathrm{C} 1)^{3}}{(I \mathrm{C} 2)^{3}}\right)
$$

## Ideal Single-Pole Multiple-Throw Switch

```
Yxx IDEAL_SW [PIN:] Pref [P1 {Pn}] [PARAM: PAR=VAL {PAR=VAL}]
+ [MODEL: MNAME]
```

Figure 6-19. Ideal Single-Pole Multiple-Throw Switch Macromodel


The ideal single-pole multiple-throw switch macromodel is an ideal switch with zero on, infinite off resistance. The switch can change its position based on which simulation analysis type is being performed and the switch state is allowed to change only between different simulation analyses.

## Model Pins

- Pref

Name of the reference node

- P1

Name of the first switch node

- Pn

Name of the $\mathrm{n}^{\text {th }}$ switch node

Table 6-10. Ideal Single-Pole Multiple-Throw Switch Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | POSITION | 0 |  | Switch position $(0,1,2, \ldots)$ |
| 2 | DC_POSITION | 0 |  | Position to which switch is set at start of DC <br> analysis |
| 3 | AC_POSITION | 0 |  | Position to which switch is set at start of AC <br> analysis |
| 3 | DCAC_POSITION | 0 |  | Position to which switch is set at start of <br> DCAC analysis (the DC analysis which runs <br> before, and as part of, AC analysis) |
| 4 | TRAN_POSITION | 0 |  | Position to which switch is set at start of <br> transient analysis |

Table 6-10. Ideal Single-Pole Multiple-Throw Switch Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 5 | IC_POSITION | 0 |  | Position to which switch is set at start of IC <br> analysis (the DC analysis which runs before, <br> and as part of, TRANSIENT analysis) |
| 6 | OFFSET | 0 | V | Offset voltage in series with common terminal |

- if POSITION $=0$, no terminal is connected to any other
- if POSITION=n, terminal Pn is connected to Pref
- if POSITION=n and OFFSET=VAL1, terminal Pn is connected to Pref through a voltage source of value=VAL1
- if XX_POSITION=n, terminal Pn is connected to Pref in XX analysis only
- Analysis specific position parameter XX_POSITION will always dominate over a position given with the POSITION parameter during the XX analysis
- The XX_POSITION parameters should be used carefully; careless use can generate discontinuities that result in convergence problems

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Example

```
ysw1 vswitch n1 n4 n2 n3
```

Specifies a voltage controlled switch ysw1 of type vswitch having input and output nodes n1 and n 4 respectively with a positive controlling node n 2 and negative controlling node n 3 .

```
ysw1 ideal_sw Pref P1 P2 PARAM: POSITION=2 OFFSET=1
```

Specifies an ideal switch ysw1 of type ideal_sw having reference node Pref, and two other switch terminals P1, P2. Since position is set to 2 with Offset voltage 1Volt, then the reference node will be connected to node P2 through a voltage source of value $=1$ Volt, while port P1 will be left un-connected.

## Triangular to Sine Wave Converter

Yxx TRI2SIN [PIN:] INP INN OUTP OUTN

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-20. Triangular to Sine Wave Converter Macromodel


This analog macromodel converts a triangular wave into a sinusoidal wave.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

Table 6-11. Triangular to Sine Wave Converter Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | GAIN | 1 |  | Gain |
| 2 | VOFF | 0 | V | Offset voltage |
| 3 | VU | 1 | V | Upper limit of input voltage |
| 4 | VL | -1 | V | Lower limit of input voltage |
| 5 | LEVEL | 1 |  | Model index |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

(1)See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
ytr1 tri2sin pin: n1 0 n2 0 param: vu=0.0 vl=8
```

Specifies a triangular to sine wave converter ytr1 of type tri2sin having input nodes n1 (+ve) and ground (-ve) with output nodes $\mathrm{n} 2(+\mathrm{ve})$ and ground (-ve). The upper and lower limits of the input voltage are declared explicitly in the instantiation line.

```
.model sto modfas voff=0.2
ytr2 tri2sin n1 n2 n3 n4 param: vu=5 model: sto
```

Specifies a triangular to sine wave converter ytr2 of type tri2sin having input nodes n 1 (+ve) and n 2 (-ve) with output nodes n 3 (+ve) and n 4 (-ve). The offset voltage is declared using the .MODEL command.

## Model Characteristics

A mathematical transformation is used to convert the triangular input to the sine output. Input signal frequency, maximum and minimum voltage are all taken into account.

If level=1 is specified (default value), the model assumes that the maximum input voltage is equal to vu and that the minimum input voltage is equal to VL .

If level=2 is specified, the model itself calculates vu and vu at runtime.

$$
\begin{aligned}
V U & =\max (V(\text { inp }, \text { inn })) \\
V L & =\min (V(\text { inp }, \text { inn })) \\
V(\text { outp }, \text { outn }) & =V O F F+V S+G A I N \times V M \times \sin (K)
\end{aligned}
$$

where

$$
\begin{aligned}
& K=(V(\text { inp }, \text { inn })-V S) \times \frac{\pi}{V M / 2} \\
& V M=\frac{(V U-V L)}{2} \\
& V S=\frac{(V U+V L)}{2}
\end{aligned}
$$

## Staircase Waveform Generator

Yxx STAIRGEN [PIN:] NP NN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-21. Staircase Waveform Generator Macromodel


A staircase waveform generator macromodel.

## Model Pins

- NP

Name of the positive input nodes

- NN

Name of the negative input nodes

Table 6-12. Staircase Waveform Generator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | VSTART | 0 | V | Start voltage |
| 2 | VDELTA | 0.1 | V | Step voltage |
| 3 | NSTEP | 10 |  | Number of voltage steps |
| 4 | TDU | $1.0 \times 10^{-4}$ | s | Period duration time |
| 5 | SLR | 1 | V/ $\mu \mathrm{s}$ | Slew rate for falling and rising edges |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

Figure 6-22. Staircase Waveform Generator Model Characteristics


## Note

The parameter set has to be consistent with the following restriction on Slew Rate:

$$
S L R \geq 200 \times(N S T E P-1) \times \frac{V D E L T A}{T D U}
$$

## Examples

```
ytr1 stairgen pin: n1 n2 param: vstart=0.0 nstep=8
```

Specifies a staircase voltage generator ytr1 of type stairgen having input node n1 with output node n 2 . The start and step voltage are declared explicitly in the instantiation line.

```
.model sto modfas nstep=5.0
•••
ytr2 stairgen n1 n2 param: vstart=1.0 vdelta=0.2 model: sto
```

Specifies a staircase voltage generator ytr2 of type stairgen having input nodes n 1 (+ve) and n 2 (-ve). The number of voltage steps is declared using the .model command.

## Sawtooth Waveform Generator

YXX SAWGEN [PIN:] NP NN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-23. Sawtooth Waveform Generator Macromodel


A sawtooth waveform generator macromodel.

## Model Pins

- NP

Name of the positive input node

- NN

Name of the negative input node

Table 6-13. Sawtooth Waveform Generator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | V0 | 0 | V | Initial voltage |
| 2 | V1 | 5 | V | Voltage magnitude |
| 3 | TDU | $1.0 \times 10^{-4}$ | s | Duration of sawtooth |
| 4 | TDEL | 0 | s | Delay time |
| 5 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

Figure 6-24. Sawtooth Waveform Generator Model Characteristics


## Examples

```
ytr1 sawgen pin: n1 n2 param: tdel=0.001
```

Specifies a sawtooth waveform generator ytr1 of type sawgen having input node n 1 with output node n 2 . The delay time is declared explicitly in the instantiation line.

```
.model sto modfas tdel=0.0001 v0=1.0
ytr2 sawgen n1 n2 param: tdel=1.0 model: sto
```

Specifies a sawtooth waveform generator ytr2 of type sawgen having input node n1 and output node n 2 . The delay time and initial voltage are declared using the .model command. Note that the delay time declared in the instantiation line overrides the delay time parameter in the . MODEL command.

## Triangular Waveform Generator

Yxx TRIGEN [PIN:] NP NN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-25. Triangular Waveform Generator Macromodel


NN
A triangle waveform generator macromodel.

## Model Pins

- NP

Name of the positive input node

- NN

Name of the negative input node

Table 6-14. Triangular Waveform Generator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | V0 | 0 | V | Initial voltage |
| 2 | V1 | 5 | V | Voltage magnitude |
| 3 | RDU | $1.0 \times 10^{-4}$ | s | Duration of first edge |
| 4 | FDU | $1.0 \times 10^{-4}$ | s | Duration of second edge |
| 5 | TDEL | 0 | s | Delay time |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. .OPTION YMFACT must be specified for $\mathbf{M}$ to work. on using this model.

Figure 6-26. Triangular Waveform Generator Model Characteristics


## Examples

```
ytr1 trigen pin: n1 n2 param: tdel=0.001
```

Specifies a sawtooth waveform generator ytrl of type trigen having input node n 1 with output node n 2 . The delay time is declared explicitly in the instantiation line.

```
.model sto modfas tdel=0.0001 v0=1.0
ytr2 trigen n1 n2 param: rdu=1.0e-3 model: sto
```

Specifies a sawtooth waveform generator ytr2 of type trigen having input node n 1 and output node n 2 . The delay time and initial voltage are declared using the .model command.

## Amplitude Modulator

YXX AMM [PIN:] INP INN OUTP OUTN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-27. Amplitude Modulator Macromodel


An amplitude modulator macromodel. The carrier frequency is specified with the $\mathbf{F C}$ parameter and the type of carrier signal is specified by level parameter (level=1- sinusoidal waveform, LEVEL=2- pulse waveform). The modulation input at lower frequencies is applied at the inp and inn terminals. The voff parameter controls the modulation depth and the final peak-to-peak voltage.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

Table 6-15. Amplitude Modulator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | LEVEL | 1 |  | Type of carrier signal 1—sinusoidal, 2-pulse |
| 2 | SLR | 10 | $\mathrm{~V} / \mu \mathrm{s}$ | Slew rate |
| 3 | VOFF | 0 | V | Offset voltage |
| 4 | FC | $1.0 \times 10^{6}$ | Hz | Carrier frequency |
| 5 | NSAM | 10 |  | Each period of the carrier signal is sampled by at least <br> NSAM points |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.
i
See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
ya1 amm pin: n1 n2 n3 n4 param: voff=0.5
```

Specifies an amplitude modulator ya1 of type amm having input nodes n1 (+ve) and n2 (-ve) with output nodes n 3 (+ve) and n4 (-ve). The offset voltage is declared explicitly in the instantiation line.

```
.model sto modfas fc=1u
ya2 amm n1 n2 n3 n4 model: sto
```

Specifies an amplitude modulator ya2 of type amm having input nodes n 1 (+ve) and n 2 (-ve) with output nodes $\mathrm{n} 3(+\mathrm{ve})$ and $\mathrm{n} 4(-\mathrm{ve})$. The carrier frequency is declared using the .model command.

## Model Characteristics

- LEVEL=1

$$
V(\text { outp }, \text { outn })=(V(\text { inp }, \text { inn })+V O F F) \times \sin (2 \pi \times T I M E \times F C)
$$

## Pulse Amplitude Modulator

Yxx PAM [PIN:] INP INN OUTP OUTN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-28. Pulse Amplitude Modulator Macromodel


A pulse amplitude modulator macromodel. The carrier frequency is specified with the $\mathbf{F C}$ parameter and the type of carrier signal is specified by the level parameter ( level=1sinusoidal waveform, LEVEL=2-pulse waveform). The modulation input at lower frequencies is applied at the inp and inn terminals. The modulation input can be centered about zero, or can be set exclusively positive or negative. The voff parameter controls the modulation depth by offsetting the modulation input.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

Table 6-16. Pulse Amplitude Modulator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | LEVEL | 1 |  | Type of carrier signal 1—sinusoidal, 2-pulse |
| 2 | SLR | 10 | $\mathrm{~V} / \mu \mathrm{s}$ | Slew rate |
| 3 | VOFF | 0 | V | Offset voltage |
| 4 | FC | $1.0 \times 10^{6}$ | Hz | Carrier frequency |
| 5 | NSAM | 10 |  | Each period of the carrier signal is sampled by at least <br> NSAM points |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.
i
See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
yp1 pam pin: n1 n2 n3 n4 param: voff=0.5
```

Specifies a pulse amplitude modulator yp1 of type pam having input nodes n 1 (+ve) and n 2 (ve) with output nodes $\mathrm{n} 3(+\mathrm{ve})$ and n 4 (-ve). The offset voltage is declared explicitly in the instantiation line.

```
.model sto modfas fc=1u
yp2 pam n1 n2 n3 n4 model: sto
```

Specifies a pulse amplitude modulator yp2 of type pam having input nodes $\mathrm{n} 1(+\mathrm{ve})$ and $\mathrm{n} 2(-$ ve) with output nodes $\mathrm{n} 3(+\mathrm{ve})$ and $\mathrm{n} 4(-\mathrm{ve})$. The carrier frequency is declared using the .mODEL command.

## Model Characteristics

- LEVEL=1

$$
V(\text { outp }, \text { outn })=\frac{V(\text { inp }, \text { inn })+V O F F}{2} \times(1+\sin (2 \pi \times T I M E \times F C))
$$

## Sample and Hold

```
Yxx SA_HO [PIN:] INP INN OUTP OUTN
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-29. Sample \& Hold Macromodel


A Sample and Hold circuit macromodel. At each sampling point the output voltage is fixed to the level of the input voltage. After the acquisition time tace has elapsed, the output voltage is kept at the level of the input voltage for a period of $1 / \mathbf{F S}$ until the next sampling point.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- Outn

Name of the negative output node

Table 6-17. Sample \& Hold Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | FS | $1.0 \times 10^{6}$ | Hz | Sampling frequency |
| 2 | TACQ | $1.0 \times 10^{-9}$ | s | Acquisition time |
| 3 | DV | 0.02 | V | Droop voltage |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. .OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

Figure 6-30. Sample \& Hold Model Characteristics


## Examples

```
ys1 sa_ho pin: n1 n2 n3 n4 param: fs=5meg
```

Specifies a Sample and Hold macromodel ys1 of type sa_ho with input nodes n1 (+ve) and n2 (ve) and output nodes $n 3(+v e)$ and $n 4(-v e)$. The sampling frequency is declared explicitly in the instantiation line.

```
.model sto modfas dv=0.05
ys2 sa_ho n1 n2 n3 n4 model: sto
```

Specifies a Sample and Hold ys2 of type sa_ho having input nodes n1 (+ve) and n2 (-ve) with output nodes n 3 (+ve) and n4 (-ve). The droop voltage is declared using the .model command.

## Track and Hold

```
Yxx TR_HO [PIN:] INP INN OUTP OUTN CRT
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-31. Track \& Hold Macromodel


A Track and Hold circuit macromodel. The model has two modes of operation depending on the logic level of the CRT voltage. Upon receiving the CRT pulse, the model swings the output voltage towards the input voltage and forces the output voltage to follow (or track) the input voltage for the remainder of the pulse. This is called the Track Mode. After the S/H pulse is removed, the model holds the output voltage at the value that the input voltage had at the instant of pulse deactivation. This is called the Hold Mode.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

- CRT

Name of the controlling voltage node

Table 6-18. Track \& Hold Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | VTH | 0.5 | V | Threshold voltage for node CRT |
| 2 | TACQ | $1.0 \times 10^{-9}$ | s | Acquisition time |
| 3 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work. on using this model.

Figure 6-32. Track \& Hold Model Characteristics


## Example

```
yt1 tr_ho pin: n1 n2 n3 n4 param: tacq=1u
```

Specifies a Track and Hold macromodel yt1 of type tr_ho having input nodes n1 (+ve) and n2 (ve) with output nodes $\mathrm{n} 3(+\mathrm{ve})$ and $\mathrm{n} 4(-\mathrm{ve})$. The acquisition time is declared explicitly in the instantiation line.

## Pulse Width Modulator

```
Yxx PWM [PIN:] CTRP CTRN OUTP OUTN
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-33. Pulse Width Modulator Macromodel


This macromodel generates a pulse width modulated signal. The duty cycle of the pulse width modulator signal can be controlled in a specified range by the input voltage.

## Model Pins

- CTRP

Name of the positive control node

- Ctrn

Name of the negative control node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

Table 6-19. Pulse Width Modulator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | DUTYMIN | 0.001 |  | Minimum duty cycle |
| 2 | DUTYMAX | 0.999 |  | Maximum duty cycle |
| 3 | CTRLMIN | 0 | V | Minimum control voltage |
| 4 | CTRLMAX | 1 | V | Maximum control voltage |
| 5 | PFREQ | $1.0 \times 10^{3}$ | Hz | Pulse frequency |
| 6 | TR | $1.0 \times 10^{-6}$ | s | Pulse rise time |
| 7 | TF | $1.0 \times 10^{-6}$ | s | Pulse fall time |
| 8 | NDELAY | 0 |  | Number of delay pulse cycles |
| 9 | PVMIN | 0 | V | Low pulse voltage |
| 10 | PVMAX | 1 | V | High pulse voltage |
| 11 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

(1)
See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Example

```
yp1 pwm pin: n1 0 n3 0 param: pvmax=5.0
```

Specifies a pulse width modulator macromodel yp1 of type pwm having input nodes n1 (+ve control) and ground (-ve control) with output nodes n3 (+ve output) and ground (-ve output). The high pulse voltage is declared explicitly in the instantiation line.

## Model Characteristics

Figure 6-34. Pulse Width Modulator Model Characteristics


Note
For correct operation of the macromodel, the following constraints must be considered: The duty cycle of the output pulse signal can only be in the following range:

$$
D U T Y C Y C L E=\frac{((T R) / 2+(T F) / 2)}{T} \ldots \frac{(T-(T R) / 2-(T F) / 2)}{T}
$$

with:

$$
\begin{aligned}
T & =\frac{1}{P F R E Q} \\
D U T Y C Y C L E & =\frac{T H I}{T}
\end{aligned}
$$

Figure 6-35. Pulse Width Modulator Duty Cycle


## Voltage Controlled Oscillator

YXX VCO [PIN:] INP INN OUTP OUTN

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-36. Voltage Controlled Oscillator Macromodel


On the output nodes a signal is generated whose frequency is dependent on the input voltage. The level parameter specifies the type for the waveform, either sinusoidal or pulse.

## Model Pins

- INP

Name of the positive input node

- InN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

Table 6-20. Voltage Controlled Oscillator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | V1 | 1 | V | Output amplitude |
| 2 | VOFF | 0 | V | Offset voltage |
| 3 | FMIN | 1 | Hz | Minimum allowed frequency-only for LEVEL=2, 3 |
| 4 | FMAX | $1.0 \times 10^{10}$ | Hz | Maximum allowed frequency-only for LEVEL=2,3 3 |
| 5 | LEVEL | 1 |  | Leves=1—Continuous sinusoidal <br> LeveL=2—Sampled sinusoidal <br> Leves=3-Sampled pulse |
| 6 | A | 0 | Hz | Polynomial parameter |
| 7 | B | 1 | $\mathrm{~Hz} / \mathrm{V}$ | Polynomial parameter |
| 8 | C | 0 | $\mathrm{~Hz} / \mathrm{V}^{2}$ | Polynomial parameter |
| 9 | D | 0 | $\mathrm{~Hz} / \mathrm{V}^{3}$ | Polynomial parameter |
| 10 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
y1 vco pin: n1 n2 n3 n4 param: voff=0.5
```

Specifies a vco model y1 having input nodes n 1 (+ve) and n2 (-ve), with output nodes n 3 (+ve) and n 4 (-ve). The offset voltage parameter is declared explicitly in the instantiation line.

```
.model tdk modfas FMIN=10k
.
ys4 vco n1 n2 n3 0 model: tdk
```

Specifies a vco model having input nodes $\mathrm{n} 1(+\mathrm{ve})$ and n 2 (-ve) with output node n 3 (+ve). The FMIN parameter is declared using the .model command.

## Model Equations

$$
v i n=V(i n p, i n n)
$$

VCO Frequency

$$
\begin{aligned}
f & =a+b \times v i n+c \times v \text { in }^{2}+d \times v \text { vin }^{3} \\
V(\text { outp }, \text { outn }) & =v o f f+v 1 \times \sin (2 \pi \times T I M E \times f)
\end{aligned}
$$

- Level=1

The frequency of the sinusoidal output signal is determined at each internal time step.

- Level=2

The frequency of the sinusoidal output is determined only once for one period of the output signal.

- Level=3

The frequency of the pulse output is determined only once for one period of the output signal.

## Peak Detector

```
YXx PEAK_D [PIN:] INP INN OUTP OUTN CRT
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-37. Peak Detector Macromodel


Positive or negative peak detection is selected using the level parameter. The peak detector tracks the input signal and hold the output at the highest (or lowest) peak found since operation of the CRT voltage or the res parameter. The input waveform is continuously compared with the stored peak value to determine whether the stored value should be updated.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- outp

Name of the positive output node

- OUtN

Name of the negative output node

- CRT

Name of the control node

Table 6-21. Peak Detector Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | VTH | 1 | V | Threshold voltage-signal on CRT pin |
| 2 | RES | 0.5 | V | If the output voltage crosses the RES value the output <br> is reset to 0 |
| 3 | SLR | 1 | V/ $\mu \mathrm{s}$ | The output signal follows the input signal with the <br> slewrate SLR |
| 4 | RSLR | 1 | V/ $\mu \mathrm{s}$ | Reset to 0 with the slewrate RSLR |
| 5 | LEVEL | 1 |  | LEVEL=1—positive peak detector <br> LEVEL=2—negative peak detector |

Table 6-21. Peak Detector Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 6 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
y1 peak_d pin: n1 n2 n3 n4 n5 param: level=2 res=-5.0
```

Specifies a peak_d model y1 having input nodes n1 (+ve) and n2 (-ve) with output nodes n3 (+ve) and n 4 (-ve) and control node n 5 . The level and res parameters are declared explicitly in the instantiation line.

```
.model tdk modfas SLR=10
...
ys4 peak_d n1 n2 n3 0 0 model:tdk
```

Specifies a peak_d model having input nodes n1 (+ve) and n2 (-ve) with output node n3 (+ve). The sLr parameter is declared using the .model command.

```
.MODEL TDK_PEAK_D MODFAS VTH=1 res=4
Vin in O pwl 0 0 10u 2 12u 4 15u 2 20u 0 45u 6 60u 0
Vcrt crt 0 pulse 0 5 0 .1u .1u 10u 25u
*Vcrt crt 0 5
Y26 PEAK_D PIN: IN 0 OUT 0 CRT PARAM: RES=5 SLR=3.0 RSLR=1.0 LEVEL=1.0
MODEL: TDK_PEAK_D
rout out 0 1k
.tran 1u 100u
.plot tran v(in)
.plot tran v(crt)
.plot tran v(out)
.end
```

In this example-see also simulation results over page-the peak detector tracks the input signal $\mathrm{V}(\mathrm{IN})$ and holds the output $\mathrm{V}(\mathrm{OUT})$ at the highest value of 4 V (seen at $12 \mu \mathrm{~s}$ ). The rising voltage on the control node $\mathrm{V}(\mathrm{CRT})$ at $25 \mu$ s causes the $\mathrm{V}(\mathrm{OUT})$ voltage to fall by $1 \mathrm{~V} / \mu \mathrm{s}$. The output then tracks the input (from $29 \mu \mathrm{~s}$ ) until it reaches the RES value ( 5 V ) at $40.8 \mu \mathrm{~s}$ and falls back to 0 .

At $46 \mu \mathrm{~s}$ V(OUT) follows $\mathrm{V}(\mathrm{IN})$ until $50 \mu$ s has passed, whereupon the input at V (CRT) causes the $\mathrm{V}(\mathrm{OUT})$ signal to return to 0 . Finally, at $55 \mu \mathrm{~s}, \mathrm{~V}(\mathrm{OUT})$ stays at the lowest $\mathrm{V}(\mathrm{IN})$ peak until an impulse on $V(C R T)$ at $75 \mu$ s causes the signal to fall to 0 .

Figure 6-38. Peak Detector Simulation Results


## Level Detector

## Single Output

Yxx LEV_D [PIN:] INP INN OUTP OUTN

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]


## Differential Output

```
Yxx LEV_D [PIN:] INP INN OUTP OUTN REF
+ [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-39. Level Detector Macromodel


The model is used to convert analog signals into bi-level signals. This is done by comparing an input signals with a reference value. Depending on the way that the parameters and number of nodes are chosen, the model works as an inverting or non-inverting zero-crossing or level detector with single or differential output and with or without hysteresis.

## Model Pins

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node

- REF

Name of the reference node. Only used for differential output.

Table 6-22. Level Detector Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | TR | 1 | $\mu \mathrm{~s}$ | Time for the output signal switching from vo to v1 |
| 2 | TF | 1 | $\mu \mathrm{~s}$ | Time for the output signal switching form v1 to vo |

Table 6-22. Level Detector Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 3 | TPD | 0 | s | Transit time through the comparator |
| 4 | V0 | 0 | V | Lower voltage level |
| 5 | V1 | 1 | V | Higher voltage level |
| 6 | VOFF | 0 | V | Is added to the potential at the node INN |
| 7 | VRL | -0.1 | V | Lower reference voltage |
| 8 | VRU | 0.1 | V | Higher reference voltage |
| 9 | M $^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
y1 lev_d pin: n1 n2 n3 0 param: v1=5 vrl=2.4 vru=2.6
```

Specifies a lev_d model y1 with single output having input nodes n1 (+ve) and n2 (-ve) with output nodes $\mathrm{n} 3(+\mathrm{ve})$. Parameters v 1 , vrl and vru are declared explicitly in the instantiation line.

```
.model tdk modfas vrl=0.0 vru=0.0
ys4 lev_d n1 n2 n3 n4 n5 model:tdk
```

Specifies a lev_d model with differential output having input nodes n1 (+ve) and n2 (-ve), with non-inverting output node n 3 and inverting output node n 4 . As reference for the output node n 5 is used. The vrl and vru parameters are declared via the . MODEL command. The above model works as a differential zero-crossing detector without hysteresis.

## Model Equations

If a rising input voltage $V I N=V(I N P)-V(I N N)-V O F F$ passes the lower reference voltage, VRL, the output signal switches from V0 to V1 during the time TR.

If a falling input voltage $V I N=V(I N P)-V(I N N)-V O F F$ passes the upper reference voltage, VRU, the output signal switches from V1 to V0 during the time TF.

The 4 node model works as a non-inverting comparator, the output signal being applied across OUtP and outn. The 5 node model works as a differential comparator. The non-inverting output signal is applied across OUTP and REF, and the inverting output signal is applied across OUTN and ref.

If the parameters VRL and VRU have the same value the model operates as zero-crossing detector.

## Logarithmic Amplifier

```
Yxx LOGAMP [PIN:] IN OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-40. Logarithmic Amplifier Macromodel


The model provides a logarithmic transfer function between the input and the output node. The signal on the output node is limited by user defined values.

## Model Pins

- IN

Name of the input node

- OUT

Name of the output node

Table 6-23. Logarithmic Amplifier Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | K | 1 |  | Gain |
| 2 | E | 1 | V | Influences the argument of the log function |
| 3 | BASE | e-natural <br> logarithm |  | Base of the logarithm |
| 4 | VMAX | 5 | V | Maximum output voltage |
| 5 | VMIN | -5 | V | Minimum output voltage |
| 6 | VSATP | 4.75 | V | Positive saturation voltage |
| 7 | VSATN | -4.75 | V | Negative saturation voltage |
| 8 | PSLOPE | 0.25 |  | Slope of Transfer Function at VSATP |
| 9 | NSLOPE | 0.25 |  | Slope of Transfer Function at VSATN |
| 10 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

## Examples

y1 logamp pin: n1 n2 param: $K=100.0$

Specifies a logamp model y1 having input node n 1 with output node n 2 . The gain parameter is declared explicitly in the instantiation line.

```
.model tdk modfas VMAX=10 VMIN=-10 VSATP=9.9 VSATN=-9.9
ys4 logamp n1 n2 model:tdk
```

Specifies a logamp model having input node n1 with output node n2. Parameters VMAX, VMIN, VSATP and VSATN are declared using the .model command.

## Model Equations

$$
v i=v(I N)
$$

if:

$$
v i \leq 1.0 \times 10^{-10}
$$

then:

$$
\begin{aligned}
& v i=1.0 \times 10^{-10} \\
& v(\text { OUT })=\text { LIMITER }\left\{-K \times \frac{1}{(\log B A S E)} \times \log \left(\frac{v i}{E}\right)\right\}
\end{aligned}
$$

Information on voltage limiting is given in the "Voltage Limiter" on page 397. Nonlimited voltages can be specified using v (yname->lin).

## Anti-logarithmic Amplifier

```
YXX EXPAMP [PIN:] IN OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 6-41. Anti-logarithmic Amplifier Macromodel


The model provides an anti-logarithmic transfer function between the input and the output node. The signal on the output node is limited by user defined values.

## Model Pins

- IN

Name of the input node

- OUT

Name of the output node

Table 6-24. Anti-logarithmic Amplifier Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | K | 1 |  | Gain |
| 2 | E | 1 | V | Influences the argument of the power function |
| 3 | BASE | e <br> exponential |  | Base of the power function |
| 4 | VMAX | 5 | V | Maximum output voltage |
| 5 | VMIN | -5 | V | Minimum output voltage |
| 6 | VSATP | 4.75 | V | Positive saturation voltage |
| 7 | VSATN | -4.75 | V | Negative saturation voltage |
| 8 | PSLOPE | 0.25 |  | Slope of Transfer Function at VSATP |
| 9 | NSLOPE | 0.25 |  | Slope of Transfer Function at VSATN |
| 10 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

y1 expamp pin: n1 n2 param: $\mathbf{K = 1 0 0 . 0}$
Specifies an expamp model y 1 having input node n 1 with output node n 2 . The gain parameter K is declared explicitly in the instantiation line.

```
.model tdk modfas VMAX=10 VMIN=-10 VSATP=9.9 VSATN=-9.9
...
ys4 expamp n1 n2 model:tdk
```

Specifies an expamp model with input node n1 and output node n2. Parameters VMAX, VMIN, VSATP and VSATN are declared using the .model command.

Model Equations

$$
v(O U T)=\operatorname{LIMITER}\left\{-K \times B A S E^{v(I N) / E}\right\}
$$

(i)

Information on voltage limiting is given in the "Voltage Limiter" on page 397. Nonlimited voltages can be specified using $v$ (yname->lin).

## Differentiator

Yxx DIFF [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-42. Differentiator Macromodel


The model provides the differentiated input signal at the output node.

## Model Pins

- IN

Name of the input node

- OUT

Name of the output node

Table 6-25. Differentiator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | K | 1 | V | Time constant |
| 2 | C 0 | 1 | V | DC value |
| 3 | SLR | $1.0 \times 10^{9}$ | V/s | Limits the slewrate of the signal on the out node |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
y1 diff pin: n1 n2 param: K=100.0
```

Specifies a diff model y1 having input node n 1 with output node n 2 . The K parameter is declared explicitly in the instantiation line.

```
.model tdk modfas CO=-1.0
ys4 diff n1 n2 model:tdk
```

Specifies a diff model having input node n 1 with output node n 2 . The C 0 parameter is declared using the .model command.

## Model Equations

DC Analysis

$$
v(O U T)=\mathrm{C} 0
$$

Transient Analysis

$$
v(O U T)=-K \times \frac{d}{d t} v(I N)
$$

## Frequency Analysis

$$
\frac{v(O U T)}{v(I N)}=-j \omega K
$$

## Integrator

Yxx INTEG [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-43. Integrator Macromodel


This model provides the integrated input signal at the output node.

## Model Pins

- IN

Name of the input node

- OUT

Name of the output node

Table 6-26. Integrator Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | K | 1 | V | Time constant |
| 2 | C 0 | 1 | V | DC value |
| 3 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
y1 integ pin: n1 n2 param: K=100.0
```

Specifies an integ model y1 having input node n 1 with output node n 2 . The K parameter is declared explicitly in the instantiation line.

```
.model tdk modfas CO=-1.0
ys4 integ n1 n2 model:tdk
```

Specifies an integ model having input node n 1 with output node n 2 . The C 0 parameter is declared using the .model command.

## Model Equations

DC Analysis

$$
v(O U T)=\mathrm{C} 0
$$

Transient Analysis

$$
v(O U T)=\frac{-1}{K} \times \int v(I N) d t+\mathrm{C} 0
$$

Frequency Analysis

$$
\frac{v(O U T)}{v(I N)}=\frac{-1}{j \omega K}
$$

## Adder, Subtractor, Multiplier and Divider

YXX NAME [PIN:] IN1 IN2 OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 6-44. Adder, Subtractor, Multiplier \& Divider Macromodels
Adder Name = add $\quad$ Subtractor Name = sub $\quad$ Multiplier Name = mult $\quad$ Divider Name = div

This model provides the specified arithmetic operation of the input signals at the output node.

## NAME Parameter

- ADD

Specifies the Adder model

- sub

Specifies the Subtractor model

- mULT

Specifies the Multiplier model

- DIV

Specifies the Divider model

## Model Pins

- IN1

Name of the first input node

- IN2

Name of the second input node

- OUT

Name of the output node

Table 6-27. Adder, Subtractor, Multiplier \& Divider Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | VMAX | 5 | V | Maximum output voltage |
| 2 | VMIN | -5 | V | Minimum output voltage |
| 3 | VSATP | 4.75 | V | Positive saturation voltage |
| 4 | VSATN | -4.75 | V | Negative saturation voltage |

Table 6-27. Adder, Subtractor, Multiplier \& Divider Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 5 | PSLOPE | 1.0 |  | Slope of Transfer Function at VSATP |
| 6 | NSLOPE | 1.0 |  | Slope of Transfer Function at VSATN |
| 7 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
y1 add pin: n1 n2 out param: vMAX=100.0
```

Specifies an adder model y1 with input nodes n1 and n2, and output node out. The VMAX parameter is declared explicitly in the instantiation line.

```
.model tdk modfas VMAX=10 VMIN=-10 VSATP=9.9 VSATN=-9.9
ys4 mult n1 n2 out model:tdk
```

Specifies a Multiplier model with input nodes n 1 and n 2 , and output node out. The VMAX, VMIN, VSATP and VSATN parameters are declared using the .mOdel command.

## Model Equations

$$
v(O U T)=\operatorname{LIMITER}\{v(\mathrm{IN} 1)[+|-|*| /] v(\mathrm{IN} 2)\}
$$

Information on voltage limiting is given in the "Voltage Limiter" on page 397.

Analog Macromodels
Adder, Subtractor, Multiplier and Divider

# Chapter 7 <br> Digital Macromodels 

## Eldo Digital Macromodels

The following digital macromodels are provided in Eldo:

| Delay | DEL |
| :--- | :--- |
| Inverter | INV |
| Exclusive-OR Gate | XOR |
| 2-Input Digital Gates | NAND, AND, NOR, OR |
| 3-Input Digital Gates | NAND, AND, NOR, OR |
| Multiple Input Digital Gates | NAND, AND, NOR, OR |

Delay
Inverter
Exclusive-OR Gate
2-Input Digital Gates
3-Input Digital Gates
Multiple Input Digital Gates

DEL
INV
XOR
NAND, AND, NOR, OR
NAND, AND, NOR, OR
NAND, AND, NOR, OR

For ADC/DAC Mixed Signal Macromodels see "Mixed Signal Macromodels" on page 462.

Digital macromodels are implemented in Eldo as time variable voltage sources whose output values are computed at execution time.

These macromodels are parameterized with threshold voltages, speed and so forth. For digital gates, parameters can be specified through a .MODEL command as is the case for semiconductor devices. Values specified in the macromodel instantiation line supersede values specified in the .MODEL command.

For more information on the .model command, see "Digital Model Definition" on page 449.

## DYND2ALOG

The option DYnd2alog can be used to dynamically calculate the threshold values VTHI and VTLO for digital macromodels using actual values of the high and low bias. The option works by taking the values from two extra pins defined by the user in the macromodel instantiation line. The value specified on the first pin provides the high voltage digital output value (VHI) and the value specified on the second pin provides the low voltage digital output value (VLO). The active threshold values VThi and VTLo, will be computed dynamically using the following equations:

```
VTHI_ACTIVE = VLO + VTHI*DV
VTLO_ACTIVE = VLO + VTLO*DV
```

VTHI and VTLO are the values specified in the .model command defining the digital macromodel or in the macromodel instance, VLO is the low output voltage value given on the second extra pin defined by the user, and DV is the voltage difference given by VHI - VLO.

1 For more information on the DYND2ALOG option, see "DYND2ALOG" on page 1018.

## Digital Model Definition

```
.MODEL MNAME LOGIC [VHI=VAL] [VLO=VAL] [VTH=VAL]
+ [VTHI=VAL] [VTLO=VAL] [TPD=VAL] [TPDUP=VAL]
+ [TPDOWN=VAL] [CIN=VAL] [DRVL=VAL] [DRVH=VAL]
```

Used for the definition of digital gate models.

## Parameters

- mNAME

Name of the model

- LOGIC

Defines the model as a digital gate model

- vHI=VAL

Output voltage for the 1 logical state. Default value is 5 V .

- vLo=VAL

Output voltage for the 0 logical state. Default value is 0 V .

- $\mathrm{VTH}=\mathrm{VAL}$

Threshold input voltage. Default value is 2.5 V .

- $\mathrm{VthI}=\mathrm{VAL}$

Input threshold voltage for the rising edge

- vtlo=val

Input threshold voltage for the falling edge

## Note



If only VTh is specified, then $\mathrm{VthI}=\mathrm{VTLO}=\mathrm{VTh}$. If both VThI and Vtlo are specified, VTh will be ignored. Ensure that the DC operating point is either above vthi or below VTLIO, otherwise the output may behave unpredictably in the first few cycles of simulation. Vthi and vtlo can be computed dynamically using the option dynd2alog.

- TPD=VAL

Transit time through the gate (time from input threshold intersection to output threshold intersection). Default value is 1 ns .

- TPDUP=VAL

Transit time (See above) for output to reach vThi volts (a value causing a change in the next gate)

- TPDOWN=VAL

Transit time (See above) for output to reach VTLO volts (a value causing a change in the next gate)

$\square$

## Note

If only TPD is specified then TPDUP=TPDOWN=TPD. If both TPDUP and TPDOWN are specified, TPD will be ignored. The slopes at the output are determined by the values of trd, trdup and trdown (See Figure 7-1 on page 450).

The above definitions of transit times and threshold voltages make sure that transit times are additive through a chain of digital operators. It is not realistic, however, to model an Eldo digital gate as a chain of single gates, as the transition at the output of such a gate would not occur immediately.

- CIN=VAL

Capacitance seen at one of the macro inputs, modeling the interconnection capacitance. All inputs are loaded with the same capacitance. CIn has no effect when the macros are linked in a chain, as the input of one gate is the output of another, which is modeled as a voltage source. Default value is zero.

- DRVL=VAL

Drive resistance for the logic 0 state

- DRVH=VAL

Drive resistance for the logic 1 state

## Note

These drive resistances are only relevant when current source modeling of Eldo logic primitive outputs is used, as selected using . OPtion ulogic. By default, if . OPtion ULOGIC is not specified, a simple voltage source is used to model logic primitive outputs.

## (1) See the "ULOGIC" on page 983.

Figure 7-1. Digital Model Parameter Thresholds


## Example

```
.model nand_1 logic vlo=5 vlo=-5 vth=0
nand#a n1 n2 o1 nand_1 tpd=2.5n cin=0.5p
```

Specifies the two input nand gate nand\#a of model type nand_1. The parameters of the gate are described using the .MODEL . . . LOGIC command and indicate that the voltages used for the logical states 0 (vlo) and 1 (vlo) are 5 V and 5 V respectively and that the threshold input voltage (vth) is set to zero. The time for the output to reach vth is 2.5 ns and the input capacitance is 0.5 pF .

The example below shows how the DYND2ALOG option is used to compute dynamic values for VHI and VLO.

```
*DYND2ALOG example
.option dynd2alog
.SUBCKT A2_020 A A0 A1 BIAS VN VP
    AND2UX01 A0 A1 A vp vn 0020
    .MODEL 0020 LOGIC
* + VHI = 5
* + VLO = 0
    + VTHI = (2/3)
    + VTLO = (1/3)
    + TPDUP = 1ns
    + TPDOWN = 1ns
    + CIN = 0.05pF
.ENDS A2_020
vn vn 0 1
vp vp 0 3
va a 0 pwl ( 0 0 10n 0 15n 5)
vb b 0 pwl ( 0 0 5n 5 20n 5 25n 0)
x1 out a b 0 vn vp a2_020
x2 out2 out a 0 vn vp a2_020
.tran 1n 100n
.plot tran v(a)
.plot tran v(b)
.plot tran v(out)
.plot tran v(out2)
.extract tran yval(v(out),20n)
.extract tran yval(v(out),10n)
.end
```

A 2-input AND gate is instantiated using the model defined in the .model statement. In the instantiation line two extra pins are defined as VP and vn. These are used by the option DYND2ALOG which has been defined at the start of the netlist. The difference between calculating the values for VHI and VLO dynamically and declaring them in the .MODEL statement can be seen using the two .Extract commands defined in the netlist. These statements will extract the values on the output waveform $v$ (out) for $x$-axis values 20 ns and 10 ns . The x -axis values define the time when the output voltage is at its high and low states, therefore correspond to VHI and VLO.

Running the simulation with the DYND2ALOG option specified and including the two extra pins will produce the values 3 V and 1 V for VHI and VLO respectively. Removing the option and the pins and including the VHI and VLO parameters in the .model statement will produce the values specified on these parameters, in this case they are 5 V and 0 V .

## Delay

DELxx IN OUT VAL

## Figure 7-2. Delay Macromodel



This macromodel describes an ideal delay element that transfers its input voltage to its output after a specified time delay, where the reference node is ground. The input impedance is infinite.

## Parameters

- IN

Name of the input node

- OUT

Name of the output node

- xx

Delay element identifier (ASCII string)

- VAL

Value of the delay in seconds

## Example

del1 a1 a2 2.0e-9
Specifies a delay element placed between nodes a1 and a2, with a delay of 2 ns .

## Inverter

```
INVxx IN OUT [REF1 REF2] [MNAME] [PAR=VAL]
```


## Figure 7-3. Inverter Macromodel



## Parameters

- IN

Name of the input node

- OUT

Name of the output node

- xx

Inverter element identifier (ASCII string)

- Ref1 Ref2

Only to be used when specifying . Option dynd2alog. Names of the pins used in the dynamic calculation of the threshold values. See "DYND2ALOG" on page 447 for more details.

- MNAME

Name of a model described with the . MODEL command

- $\quad$ PAR=VAL

A direct assignment of a .MODEL command parameter

## Example

```
.model inv logic vhi=5 vlo=-5 vthi=1.0 vtlo=1.0
+ tpd=2.5n cin=0.5p
inv44 i1 o1 inv
```

Specifies the inverter inv44 of model type inv placed between the nodes i1 and o1. The parameters of the inverter are specified using the .MODEL command.

```
inv44 il o1 vhi=5 vlo=-5 vthi=1.0 vtlo=1.0
+ tpd=2.5n cin=0.5p
```

Specifies the same inverter as above but with its parameters assigned directly instead of using the . MODEL command.
i For more information, refer to the ".MODEL" on page 723.

## Exclusive-OR Gate

XORxx IN1 IN2 OUT [REF1 REF2] [MNAME] [PAR=VAL]

## Parameters

- IN1, IN2

Names of the input nodes

- OUT

Name of the otput node

- xx

Exclusive-OR element identifier (ASCII string)

- REF1 REF2

Only to be used when specifying . option dynd2alog. Names of the pins used in the dynamic calculation of the threshold values. See "DYND2ALOG" on page 447 for more details.

- MNAME

Name of a model described with the .model command

- $\quad$ PAR=VAL

A direct assignment of a .MODEL command parameter

## Example

```
.model xor logic vhi=5 vlo=-5 vthi=1.0 vtlo=1.0
+ tpd=2.5n cin=0.5p
xor44 i1 i2 o1 xor
```

Specifies the exclusive-OR gate xor44 of model type xor placed between the nodes i1, i2 and o1. The parameters of the exclusive-OR are specified using the .model command.

```
xor44 i1 i2 ol vhi=5 vlo=-5 vthi=1.0 vtlo=1.0
+ tpd=2.5n cin=0.5p
```

Specifies the same exclusive-OR as above but with its parameters assigned directly instead of using the .MODEL command.

[^9]
## 2-Input Digital Gates

DGATExx IN1 IN2 OUT [REF1 REF2] [MNAME] [PAR=VAL]

## Parameters

- DGATE

Digital gate type
Table 7-1. 2-Input Digital Gate Types

| Gate Type | Function |
| :--- | :--- |
| NAND | NAND gate |
| AND | AND gate |
| NOR | NOR gate |
| OR | OR gate |

- xx

Digital gate identifier (ASCII string)

## Note

The first ASCII character of the gate identifier (xx) must not be a 3 since this would indicate a triple-input gate.

- IN1, IN2

Names of the input nodes

- OUT

Name of the output node

- REF1 REF2

Only to be used when specifying . option dynd2alog. Names of the pins used in the dynamic calculation of the threshold values. See "DYND2ALOG" on page 447 for more details.

- MNAME

Name of a model described with the .model command

- $\quad$ PAR=VAL

A direct assignment of a .MODEL command parameter

## Examples

*.MODEL definition
.model nand_1 logic vhi=5 vlo=-5 vth=0 tpd=2.5n cin=0.5p
nand4 n1 n2 o1 nand_1

Specifies a two input NAND gate nand4 of model type nand_1 with input nodes n1 and n2 and output node o1. The model parameters of the NAND gate are described using the .model command.
nand4 n 1 n 2 o1 vhi=5 vlo $=-5$ vth $=0$ tpd=2.5n cin=0.5p
Specifies the same NAND gate as above but with its parameters assigned directly instead of with the . MODEL command.

## 1 For more information, refer to the ".MODEL" on page 723.

## 3-Input Digital Gates

DGATExx IN1 IN2 IN3 OUT [REF1 REF2] [MNAME] [PAR=VAL]

## Parameters

- DGATE

Digital gate type
Table 7-2. 3-Input Digital Gate Types

| Gate Type | Function |
| :--- | :--- |
| NAND3 | NAND gate |
| AND3 | AND gate |
| NOR3 | NOR gate |
| OR3 | OR gate |

- xx

Digital gate identifier (ASCII string)

- IN1, IN2, IN3

Names of the input nodes

- out

Name of the output node

- Ref1 Ref2

Only to be used when specifying . Option dynd2alog. Names of the pins used in the dynamic calculation of the threshold values. See "DYND2ALOG" on page 447 for more details.

- MNAME

Name of a model described with the .model command

- $\quad$ PAR=VAL

A direct assignment of a .MODEL command parameter

## Examples

```
*AND3 .MODEL definition
.model and_1 logic vhi=5 vlo=-5 vth=0 tpd=2.5n cin=0.5p
...
*main circuit
and3_1 n1 n2 n3 o1 and_1
```

Specifies a three input AND gate and3_1 with input nodes n1, n2 and n3 and output node o1. The parameters of the and gate are described in the model and_1 using the .mOdes command.
and3_1 n1 n2 n3 o1 vhi=5 vlo=-5 vth=0 tpd=2.5n cin=0.5p

Specifies the same AND gate as above but with its parameters assigned directly instead of with the .model command.
(1) For more information, refer to ".MODEL" on page 723.

## Multiple Input Digital Gates

DGATExx IN1 IN2...\{INX\} OUT [REF1 REF2] MNAME [PAR=VAL]
Multiple Input Digital Gates Macromodel.

## Parameters

- DGATE

Digital gate type
Table 7-3. Multiple Input Digital Gate Types

| Gate Type | Function |
| :--- | :--- |
| NAND\# | NAND gate |
| AND\# | AND gate |
| NOR\# | NOR gate |
| OR\# | OR gate |

- $x \mathrm{x}$

Digital gate identifier (ASCII string)

- IN1, IN2,... $\{$ INX $\}$

Names of the input nodes

- OUT

Name of the output node

- REF1 REF2

Only to be used when specifying . option dynd2alog. Names of the pins used in the dynamic calculation of the threshold values. See "DYND2ALOG" on page 447 for more details.

- MNAME

Name of a model described with the .model command

- PAR=VAL

A direct assignment of a .MODEL command parameter

## Examples

*AND\# . MODEL definition
.model and_1 logic vhi=5 vlo=-5 vth=0 tpd=2.5n cin=0.5p
-••
*main circuit
and\#_1 n1 n2 n3 n4 o1 and_1
Specifies an AND gate and\#_1 with four input nodes n1, n2, n3 and n4 and an output node o1. The parameters of the AND gate are described in the model and_1 using the .modes command.

```
and#_1 n1 n2 n3 n4 o1 and_1 vhi=5 vlo=0 vth=2.5
+ tpd=2.5n cin=0.5p
```

In this example, the parameters on the instantiation line override the parameters in the .mOdel command.

For more information, refer to ".MODEL" on page 723.

## Mixed Signal Macromodels

The following mixed signal macromodels are provided in Eldo:

| Analog to Digital Converter | ADC |
| :--- | :--- |
| Digital to Analog Converter | DAC |

1 For Digital Macromodels, see "Eldo Digital Macromodels" on page 447.

## Analog to Digital Converter <br> ```ADCxx CLK IN OUTSB{OUTSB} [EDGE=VAL] [VTH=VAL] [VHI=VAL]``` <br> + [VLO=VAL] [VINF=VAL] [VSUP=VAL] [TCOM=VAL] [TPD=VAL]

Figure 7-4. Analog to Digital Converter Macromodel


The analog to digital converter (ADC) is defined by the clock, the analog input and a number of digital outputs. Outputs are computed only when the clock validates the input, i.e. on the rising or falling edge depending on the value of the edge parameter.

## Parameters

- xx

Analog to digital converter identifier (ASCII string)

- CLK

Name of the clock node

- IN

Name of the analog input node

- OUTSB

Digital output nodes (MSB to LSB). A maximum of 31 bits can be defined when using this macromodel.

- EDGE=VAL

EDGE $=1$ to validate the output on the rising edge of the clock
$E D G E=-1$ to validate the output on the falling edge of the clock. Default value is 1 .

- $\mathrm{Vth}=\mathrm{VAL}$

Threshold voltage for the clock. Default value is 2.5 V .

- $\mathrm{VHI}=\mathrm{VAL}$

Voltage corresponding to the 1 output logical state. Default value is 5 V .

- vlo=val

Voltage corresponding to the 0 output logical state. Default value is 0 V .

- VINF=VAL

Lower input voltage. If an analog voltage entering the ADC is lower than this value, all outputs remain at vio. Default value is 0 V .

- VSUP=VAL

Upper input voltage. If an analog voltage entering the ADC is higher than this value, all outputs remain at vhr. Default value is 5 V .

- $\mathbf{T C O M}=\mathrm{VAL}$

Time for the outputs to change from vhi to vio or vice versa. Default value is 1 ns .

- TPD=VAL

Transit time through the converter. The output will start changing TPD seconds after the clock validates the input. Default value is 10 ns .

## Example

```
adc_1 clk in d4 d3 d2 d1 edge=-1 vth=1 vhi=5
+ vlo=0 vinf=1.0 vsup=4.0 tcom=5n tpd=2n
```

Specifies an ADC named adc_1 with clock node clk, analog input node in and digital output nodes d 4 (MSB), d3, d2 and d1 (LSB). The output is validated on the falling edge of the clock, with the threshold voltage for the clock being 1 V . The voltages corresponding to logical 1 and 0 are 5 V and 0 V respectively. The upper and lower threshold voltages in order for the output to remain high or low are 4 V and 1 V respectively with the time for the ADC to change from a high to a low voltage being 5 ns . Finally, the transit time through the ADC is 2 ns .

## Digital to Analog Converter

DACxx CLK INSB\{INSB\} OUT [EDGE=VAL] [VTH=VAL] [VTIN=VAL]

+ [VHI=VAL] [VLO=VAL] [TPD=VAL] [SL=VAL]
Figure 7-5. Digital to Analog Converter Macromodel


The digital to analog converter (DAC) is defined by the clock, the digital inputs and the analog output. The output is computed only when the clock validates the input, i.e. on the rising or falling edge depending on the value of the EDGE parameter.

## Parameters

- xx

Digital to analog converter identifier (ASCII string)

- CLK

Name of the clock node

- INSB

Name of the digital input nodes (MSB to LSB)

- OUT

Name of the analog output node. A maximum of 31 bits can be defined when using this macromodel.

- EDGE=VAL

EDGE=1 validates the output on the rising edge of the clock
EDGE=-1 validates the output on the falling edge of the clock. Default value is 1 .

- $\mathrm{V} T \mathrm{H}=\mathrm{VAL}$

Threshold voltage for the clock. Default value is 2.5 V .

- Vtin=VAL

Threshold voltage for the inputs. Default value is 2.5 V .

- $\mathrm{VHI}=\mathrm{VAL}$

Voltage output when all inputs are above vrin. Default value is 5 V .

- $\mathrm{VLO}=\mathrm{VAL}$

Voltage output when all inputs are below vitin. Default value is 0 V .

- TPD=VAL

Transit time through the converter. The output will start changing trd seconds after the clock validates the output. Default value is 10 ns .

- $\mathbf{S L}=\mathrm{VAL}$

Slope at the output, in $\mathrm{Vs}^{-1}$. Default value is $0.1 \times 10^{9} \mathrm{Vs}^{-1}\left(0.1 \mathrm{Vns}^{-1}\right)$.

## Example

```
dac2 clk s4 s3 s2 s1 out vth=2 vlo=1 tpd=5n sl=1e9
```

+ vtin=2.2 vth=2.5

Specifies a DAC named dac2 with clock node clk, digital inputs s4 (MSB), s3, s2 and s1 (LSB) and analog output out. The threshold voltages for the clock and inputs are 2.5 V and 2.2 V respectively. When all inputs are above the input threshold voltage, the output voltage is equal to 2 V , and when they are all below it the output voltage is equal to 1 V . Finally, the slope of the output is defined as $1 \mathrm{Vns}^{-1}$.

## Eldo Magnetic Macromodels

The following magnetic macromodels are provided in Eldo:

Transformer Winding
Non-linear Magnetic Core 1
Non-linear Magnetic Core 2
Linear Magnetic Core
Magnetic Air Gap
Transformer (Variable \# of Windings)
Ideal Transformer

WINDING
NLCORE1
NLCORE2
LINCORE
AIRGAP
LVTRANS
JTRAN

## Transformer Winding

Yxx WINDING [PIN:] E1 E2 M1 M2 [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 8-1. Transformer Winding Macromodel
WINDING


This is a macromodel for a winding describing the interaction between the electrical and magnetic domain of a wire wrapped around a linear/non-linear material.

## Model Pins

- E1

Name of the first electrical pin

- E2

Name of the second electrical pin

- M1

Name of the first magnetic pin

- M2

Name of the second magnetic pin

Table 8-1. Transformer Winding Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | N | $1.0 \times 10^{3}$ |  | Number of turns |
| 2 | R | $1.0 \times 10^{-2}$ | $\Omega$ | Resistance of the winding |
| 3 | K | 1.0 |  | Coupling coefficient of the winding to the core. May be <br> in the range $0.0 \leq \mathrm{K} \leq 1.0$ |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Example

ymod5 winding n1 n2 p1 p2
Specifies a winding ymod5 of type winding having electrical pins n 1 and n 2 with magnetic pins p1 and p2. Default model parameters are used.

## Non-linear Magnetic Core 1

Yxx NLCORE1 [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 8-2. Non-linear Magnetic Core 1 Macromodel
NLCORE1


This is a macromodel for a non-linear magnetic core. It is a physically based mathematical model of the ferromagnetic hysteresis, which includes the following effects:

- Mean field approach for domain coupling.
- Domain wall motion.
- Pinning of domain walls on defect sites.
- Frequency dependent domain wall pinning.

The source information for this macromodel can be found in the following technical articles:
D.C. Jiles, D.L. Atherton, "Theory of Ferromagnetic Hysteresis" "Journal of Magnetism and Magnetic Materials," Vol. 61, Sept. 1986, pp 48-60. R. Brachtendorf, R. Laur, "Modeling of Magnetic Elements including Frequency Effects." 2.GME/ITG Workshop "Entwicklung von Analogschaltungen mit CAE-Methoden." Ilmenau, Germany, March 1993.

## Model Pins

- MP

Name of the input magnetic node

- MN

Name of the output magnetic node

Table 8-2. Non-linear Magnetic Core 1 Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | AREA | $1.0 \times 10^{-4}$ | $\mathrm{~m}^{2}$ | Core area |
| 2 | LEN | $1.0 \times 10^{-3}$ | m | Length of the magnetic path |
| 3 | MS | $1.7 \times 10^{6}$ | $\mathrm{Am}^{-1}$ | Saturation magnetization |
| 4 | ALPHA | $1.0 \times 10^{-3}$ |  | Domain coupling coefficient (mean field parameter) |

Table 8-2. Non-linear Magnetic Core 1 Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 5 | A | $1.0 \times 10^{3}$ | $\mathrm{Am}^{-1}$ | Domain density |
| 6 | K | $1.0 \times 10^{3}$ | $\mathrm{Am}^{-1}$ | Domain wall pinning coefficient |
| 7 | C | 0.1 |  | Reversible wall motion coefficient |
| 8 | KF | $1.0 \times 10^{-6}$ |  | Frequency dependent domain wall pinning coefficient |
| 9 | LEVEL | 1 |  | Selector for Anhysterisis model <br> LEVEL=1-Langevin function <br> LEVEL=2-Tangens-Hyperbolicus (tanh) |
| 10 | MD | $1.0 \times 10^{-5}$ |  | Delay element for irreversible magnetization |
| 11 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Example

ymod1 nlcore1 n1 n2
Specifies a non-linear core ymod1 of type nlcore1 having input magnetic node n 1 and output magnetic node n2. Default model parameters are used.

## Model Characteristics

Typical hysteresis curves for this macromodel are shown on the following page:

Figure 8-3. Symmetric B-H loops with Different Amplitudes


Figure 8-4. Asymmetric Minor Loops


## Non-linear Magnetic Core 2

Yxx NLCORE2 [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 8-5. Non-linear Magnetic Core 2 Macromodel
NLCORE2


A non-linear magnetic core macromodel. It describes the hysteretic behavior of a magnetic material including the temperature and frequency dependence of the hysteresis characteristic.

The source information for this macromodel can be found in the following article: Chan, Vladimirescu, Gao, Liebmann, Valainis, "Non-linear Transformer Model for Circuit Simulation" 'IEEE Transactions on Computer-Aided Design,' Vol. 10, No. 4, April 1991.

## Model Pins

- MP

Name of the input magnetic node

- MN

Name of the output magnetic node

Table 8-3. Non-linear Magnetic Core 2

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | AREA | $1.0 \times 10^{-4}$ | $\mathrm{~m}^{2}$ | Core area |
| 2 | LEN | $5.0 \times 10^{-2}$ | m | Length of the magnetic path |
| 3 | HC | 10.0 | $\mathrm{Am}^{-1}$ | Coercive magnetic field strength |
| 4 | BR | 0.1 | $\mathrm{Vsm}^{-2}$ | Remnant magnetic flux density |
| 5 | BS | 1.0 | $\mathrm{Vsm}^{-2}$ | Saturation magnetic flux density |
| 6 | CEPS | $1.0 \times 10^{-2}$ |  | Coefficient influencing the internal model accuracy |
| 7 | TBS | 0.0 | $\mathrm{~K}^{-1}$ | Temperature coefficient for BS |
| 8 | TBR | 0.0 | $\mathrm{~K}^{-1}$ | Temperature coefficient for BR |
| 9 | THC | 0.0 | $\mathrm{~K}^{-1}$ | Temperature coefficient for HC |
| 10 | FNOM | $1.0 \times 10^{3}$ | Hz | Working frequency |
| 11 | FC1 | 1.0 |  | First frequency coefficient |

Table 8-3. Non-linear Magnetic Core 2

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 12 | FC 2 | 0.0 | $\mathrm{~Hz}^{-1}$ | Second frequency coefficient |
| 13 | FC 3 | 0.0 |  | Third frequency coefficient |
| 14 | MYI | 1000.0 |  | Initial relative permeability of the core material |
| 15 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Examples

```
ymod1 nlcore2 n1 n2
```

Specifies a non-linear magnetic core ymod1 of type nlcore 2 having input magnetic node n 1 and output magnetic node n2. Default model parameters are used.

```
.model mod modfas bs=0.5 br=0.2 hc=20.0
ycore1 nlcore2 n1 n2 model: mod
```

Specifies a non-linear magnetic core ycore1 of type nlcore2 with input magnetic node n 1 and output magnetic node n 2 . Characteristic points of the hysteresis curve are declared using the .MODEL command.

## Model Characteristics

Typical hysteresis curves for this macromodel are shown on the following page:

## Figure 8-6. Symmetric B-H loops with Different Amplitudes



Figure 8-7. Asymmetric Minor Loops


## Linear Magnetic Core

Yxx LINCORE [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 8-8. Linear Magnetic Core Macromodel


This is a macromodel for a magnetic core with linear B-H characteristics.

## Model Pins

- MP

Name of the input magnetic node

- MN

Name of the output magnetic node

Table 8-4. Linear Magnetic Core Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | AREA | $1.0 \times 10^{-4}$ | $\mathrm{~m}^{2}$ | Core area |
| 2 | LEN | $1.0 \times 10^{-2}$ | m | Length of the magnetic path |
| 3 | MYR | 1 |  | Relative permeability of core material |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |
| 1. OPTION YMFACT must be specified for $\mathbf{M}$ to work. |  |  |  |  |

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Example

```
ymod1 lincore n1 n2
```

Specifies a linear core ymod1 of type lincore having input magnetic node n 1 and output magnetic node n2. Default model parameters are used.

## Magnetic Air Gap

Yxx AIRGAP [PIN:] MP MN [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 8-9. Magnetic Air Gap Macromodel
AIRGAP


A linear resistor macromodel modeling the magnetic resistance of an air gap inside a magnetic core.

## Model Pins

- MP

Name of the input magnetic node

- MN

Name of the output magnetic node

Table 8-5. Magnetic Air Gap Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | AGAP | $1.0 \times 10^{-4}$ | $\mathrm{~m}^{2}$ | Cross-sectional area of the air gap |
| 2 | LGAP | $1.0 \times 10^{-2}$ | m | Length of the air gap |
| 3 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

See "General Notes on the Use of FAS Macromodels" on page 380 for additional notes on using this model.

## Example

```
ymod1 airgap n1 n2
```

Specifies a magnetic air gap ymod1 of type airgap having input magnetic node n 1 and output magnetic node n2. Default model parameters are used.

## Transformer (Variable \# of Windings)

Yxx LVTRANS [PIN:] P1P P1N P2P P2N \{PNP PNN\}

+ [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 8-10. Transformer (Variable \# of Windings) Macromodel
LVTRANS


A macromodel for a linear transformer with a variable number (maximum is 8 ) of windings. The number of pins at instantiation determines the number of transformer windings and hence the number of required parameters.

## Model Pins

- PNP

Name of the positive pin of the nth transformer winding (dependent on the number of transformer windings declared).

- PNN

Name of the negative pin of the nth transformer winding (dependent on the number of transformer windings declared).

Table 8-6. Transformer Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | $\mathrm{~L}_{\mathrm{ij}}$ | $1.0 \times 10^{-3}$ | H | Element ij of inductance matrix |
| 2 | $\mathrm{R}_{\mathrm{i}}$ | $1.0 \times 10^{-3}$ | $\Omega$ | Element i of winding resistance vector |
| 3 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

Where $\mathrm{i}=1$ to number of windings, $\mathrm{j}=1$ to number of windings.

## Example 1-Transformer with 2 Windings

```
ytr1 lvtrans p1 p2 s1 s2 param: 111=2.0e-3 112=1.0e-3
+ 121=2.0e-3 122=2.0e-3 r1=1 r2=10
```

Specifies a transformer ytr1 of type lvtrans with two windings. The first transformer winding has pins p1 (+ve) and p2 (-ve) and the second winding has pins s1 (+ve) and s2 (-ve). The model equations given below show the inductance matrix and the resistance vector for the above transformer.

$$
\left[\begin{array}{l}
v(\mathrm{p} 1, \mathrm{p} 2) \\
v(\mathrm{~s} 1, \mathrm{~s} 2)
\end{array}\right]=\left[\begin{array}{ll}
\mathrm{L} 11 & \mathrm{~L} 21 \\
\mathrm{~L} 12 & \mathrm{~L} 22
\end{array}\right] \cdot\left[\begin{array}{l}
\frac{d}{d t} \mathrm{i} 1 \\
\frac{d}{d t} \mathrm{i} 2
\end{array}\right]+\left[\begin{array}{cc}
\mathrm{R} 1 & 0 \\
0 & \mathrm{R} 2
\end{array}\right] \cdot\left[\begin{array}{l}
\mathrm{i} 1 \\
\mathrm{i} 2
\end{array}\right]
$$

where $\boldsymbol{i 1}$ is the current in the first winding and $\boldsymbol{i} \mathbf{2}$ is the current in the second winding.

## Example 2—Transformer with 3 Windings

```
ytr3 lvtrans p1 p2 s1 s2 t1 t2
```

Specifies a transformer ytr3 of type lvtrans with three windings. The first transformer winding has pins p1 (+ve) and p2 (-ve), the second winding has pins s1 (+ve) and s2 (-ve) and the third winding has pins $\mathrm{t} 1(+\mathrm{ve})$ and $\mathrm{t} 2(-\mathrm{ve})$. Default parameters are used. The model equations given below show the inductance matrix and the resistance vector for the above transformer.

$$
\left[\begin{array}{l}
V(\mathrm{p} 1, \mathrm{p} 2) \\
V(\mathrm{~s} 1, \mathrm{~s} 2) \\
V(\mathrm{t} 1, \mathrm{t} 2)
\end{array}\right]=\left[\begin{array}{lll}
\mathrm{L} 11 & \mathrm{~L} 21 & \mathrm{~L} 31 \\
\mathrm{~L} 12 & \mathrm{~L} 22 & \mathrm{~L} 32 \\
\mathrm{~L} 13 & \mathrm{~L} 23 & \mathrm{~L} 33
\end{array}\right] \cdot\left[\begin{array}{l}
\frac{d}{d t} \mathrm{i} 1 \\
\frac{d}{d t} \mathrm{i} 2 \\
\frac{d}{d t} \mathrm{i} 3
\end{array}\right]+\left[\begin{array}{l}
\mathrm{R} 1 \\
\mathrm{R} 2 \\
\mathrm{R} 3
\end{array}\right] \cdot\left[\begin{array}{l}
\mathrm{i} 1 \\
\mathrm{i} 2 \\
\mathrm{i} 3
\end{array}\right]
$$

where $\boldsymbol{i 1}$ is the current flowing in the first winding, $\boldsymbol{i 2}$ is the current in the second winding and $\mathbf{i 3}$ is the current in the third winding.

## Ideal Transformer

Yxx JTRAN N1 N2 N3 N4 [PARAM: A=VAL]
Figure 8-11. Ideal Transformer Macromodel


A macromodel for an ideal transformer.

## Parameters

- N1, N2, N3, N4

Ideal transformer nodes as shown in the figure above

- A

Transformer's turns ratio

## Example

AC simulation of an ideal transformer (1:2).

```
.param tran_ratio=2
Ytran jtran ain 0 aout O PARAM: a=tran_ratio
Vin Xin 0 AC 10
Vdummy1 Xin ain AC 0
Vdummy2 aout Xout AC 0
Rout Xout 0 1
.defwave voltage_gain=V(aout)/V(ain)
.defwave current_gain=I(Vdummy2)/I(Vdummy1)
.ac dec 10 1 1g
.plot ac wm(voltage_gain)
.plot ac wp(voltage_gain)
.plot ac wm(current_gain)
.plot ac wp(current_gain)
.end
```


## Chapter 9 Switched Capacitor Macromodels

## Introduction

This chapter is concerned with the area of Switched Capacitor Macromodels. Within the subject area of Switched Capacitor Macromodels, there are two separate types to be distinguished between and they are:

- Switch Level Representation
- Z-domain Representation


## Switch Level Representation

The following macromodels have a Charge Conservation characteristic and are the key elements for Switched Capacitor (SC) applications, where the MOS analog switches are represented by an approximate general linearized model of a non-ideal switch.

All these models are Kirchhoff type elements and can be applied as normal components in an electronic circuit in the same way as other models such as bipolar transistors, diodes, noise sources, and so on.

All switched capacitor networks built using these models can be analyzed in the time domain without any restrictions, but an AC analysis would be meaningless. If an AC analysis is needed, particularly for switched capacitor filter applications, then another type of model representation for the switched capacitor circuit is required.

## (1) Refer to "Z-domain Representation" on page 491.

## Macromodels

Below is a list of the Eldo Macromodels which are described throughout this chapter:

Operational Amplifier
Switch
Ideal Operational Amplifier
Inverting Switched Capacitor

OPAXX
Sxx
Yxx SC_IDEAL
Yxx SC_I

| Non-inverting Switched Capacitor | YXX SC_N |
| :---: | :---: |
| Parallel Switched Capacitor | Yxx SC_P |
| Serial Switched Capacitor | Yxx SC_S1 |
|  | YXX SC_S2 |
| Serial-parallel Switched Capacitor | Yxx SC_SP1 |
|  | Yxx SC_SP2 |
| Bi-linear Switched Capacitor | Yxx SC_B |
| Unswitched Capacitor | Yxx SC_U |

## Operational Amplifier

```
OPAxx INP INN OUTP OUTN [MNAME] [LEVEL=VAL] [VOFF=VAL]
+ [SL=VAL] [CIN=VAL] [RS=VAL] [VSAT=VAL] [VSATM=VAL]
+ [GAIN=VAL] [FC=VAL] [FNDP=VAL] [IMAX=VAL] [CMRR=VAL]
```

Figure 9-1. Operational Amplifier Macromodel


A macromodel for single- and two-stage operational amplifiers. This syntax supersedes that of all previous Eldo versions. Old syntax is still supported, but no longer recommended.

## Parameters

- $x x$

Amplifier name

- INP

Name of the positive input node

- INN

Name of the negative input node

- OUTP

Name of the positive output node

- OUTN

Name of the negative output node. For single-stage op-amps this must be set to zero.
When specified, the optional parameters listed below override default values set via the .mODEL command.

- MNAME

The model name, as described in the .model command

- LEVEL=VAL

1 for single-stage, 2 for two-stage op-amps. Default value is 2 . The Level parameter cannot be changed in the instantiation line, only in the .model card.

- VOFF=VAL

Offset voltage in volts. Default value is 0 V .

- $\quad \mathbf{S L}=$ VAL

Slew rate in volts/second for two-stage op-amps only. Default is $1.0 \times 10^{6} \mathrm{~V} / \mathrm{s}$.

- CIN=VAL

Input capacitance in farads. Default value is 0F.

- RS=VAL

Output resistance in ohms. Default value is $1 \mathrm{M} \Omega$ for single-stage and $10 \mathrm{M} \Omega$ for two-stage op-amps.

- VSAT=VAL

Symmetrical saturation voltage of $\pm$ vSAT in volts. Default value is 5 V .

- VSATM=VAL

Asymmetrical saturation voltage, with vSATN as lower and vSAt as upper saturation voltage. Default is -5 V .

## Note

vSAT and vSATm must be declared together if they are used in the instantiation line.

- GAIN=VAL

Linear or dB scaling factor. Default value is 1000 .

- $\quad \mathbf{F C}=V A L$

Cut-off frequency in Hertz for two-stage amplifiers only. Default value is 1 kHz .

- $\quad \mathbf{F N D P}=\mathrm{VAL}$

Non-dominant pole frequency in Hertz for single-stage op-amps only. Default value is 1 kHz .

- $\operatorname{IMAX}=\mathrm{VAL}$

Saturation current in amps for single-stage op-amps only. Default value is 100 mA .

- CMRR=VAL

Common mode rejection ratio, linear or in dB. Default value is zero.

## Note

When using an operational amplifier macromodel, it is recommended that the default simulator accuracy (eps parameter) is increased from 1 mV to $1 \mu \mathrm{~V}$ using the . OPtion command. The amplifier model calculates a current at its output and expects a voltage at its input. It is recommended, therefore that a resistor be connected between the input and output of cascaded amplifier macromodels, as shown below.

Figure 9-2. Cascaded Amplifier Macromodel


## Operational Amplifier Model

.MODEL MNAME OPA [PAR=VAL]

## Equivalent Circuit (Single-stage Amplifier)

Figure 9-3. Equivalent Circuit (Single-stage Amplifier)


Model Equations (Single-stage Amplifier)
$\boldsymbol{R}=1 \mathrm{k} \Omega$ which cannot be changed.

$$
C=\frac{1}{2 \pi \times R \times F N D P}
$$

For DC analysis, $\boldsymbol{C}$ is open circuit, therefore:

$$
V 1=G A I N \times V E
$$

## Equivalent Circuit (Two-stage Amplifier)

Figure 9-4. Equivalent Circuit (Two-stage Amplifier)


Model Equations (Two-stage Amplifier)
$\boldsymbol{R}=1 \mathrm{k} \Omega$ which cannot be changed.

$$
\begin{aligned}
& C=\frac{1}{2 \pi \times R \times F C} \\
& I M A X=S L \times C
\end{aligned}
$$

For DC analysis, $\boldsymbol{C}$ is short circuit, therefore:

$$
I=\frac{(G A I N \times V E)}{R}
$$

If $I<I M A X$ then:

$$
\mathrm{V} 1=G A I N \times V E
$$

else:V1 $=I M A X \times R$

Table 9-1. Operational Amplifier Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | LEVEL | 2 |  | Amplifier index |
| 2 | VOFF | 0 | V | Offset voltage |
| 3 | SL | $1.0 \times 10^{6}$ | $\mathrm{Vs}^{-1}$ | Slew rate (two-stage) |
| 4 | CIN | 0 | F | Input capacitance |
| 5 | RS | $1.0 \times 10^{6}$ | $\Omega$ | Output resistance (single-stage) |
|  |  | 1 | $\Omega$ | Output resistance (two-stage) |
| 6 | VSAT | 5 | V | Symmetrical saturation voltage |
| 7 | VSATN | -5 | V | Unsymmetrical saturation voltage |
| 8 | GAIN | $1.0 \times 10^{3}$ |  | Scaling factor |
| 9 | FC | $1.0 \times 10^{3}$ | Hz | Cut-off frequency (two-stage) |
| 10 | FNDP | $1.0 \times 10^{8}$ | Hz | Pole frequency (single-stage) |
| 11 | IMAX | 0.1 | A | Saturation current (single-stage) |
| 10 | CMRR | 0 |  | Common mode rejection ratio |

## Example

```
*OPAMP model definition
.model ampop opa level=2 voff=0 sl=50e06
+ cin=0 rs=10 vsat=5 gain=5000 fc=5000
*main circuit
opa1 n2 n1 n3 0 ampop
```

Specifies the operational amplifier opa1 of model type ampop having input nodes n2 (+ve) and n1 (-ve) with output nodes n3 (+ve) and ground (-ve). The electrical parameters of the op-amp are specified using the .model command.

## Switch

Sxx NC N1 N2 [MNAME] [RON [CREC]]
Figure 9-5. Switch Macromodel


## Parameters

- xx

Switch name

- NC

Switch voltage controlling node

- N1

Name of the node 1

- N 2

Name of the node 2

- mNAME

Model name, as described in the .mODEL command

- RON
"On" resistance of the switch in ohms. Default is $1 \mathrm{k} \Omega$. If $\mathrm{RON} \leq 0$, then it is reset to $1 \mathrm{k} \Omega$.
- CREC

Overlap capacitance, modeling Charge Injection. Default is zero.
Note
Switch macromodels may only be used in transient noise or DC simulations.

## Example

$\mathbf{s} 23$ c n2 n6 2000 0.02e-12
Specifies a switch named s23 placed between nodes n 2 and n 6 , with controlling node c , having a $2 \mathrm{k} \Omega$ "on" resistance and 0.02 pF overlap capacitance.

## Switch Model

| .MODEL MNAME NSW [PAR=VAL] | ! NMOS |
| :--- | :--- |
| .MODEL MNAME PSW [PAR=VAL] | ! PMOS |

## Model Equivalent Circuit

Figure 9-6. Closed Switch Equivalent Circuit


Figure 9-7. Open Switch Equivalent Circuit Status-Open switch


Figure 9-8. NMOS Switch


Figure 9-9. PMOS Switch


Table 9-2. Switch Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 2 | VTH | 0.47 | V | Threshold voltage (for enhanced NMOS) |
|  |  | -0.47 | V | Threshold voltage (for enhanced PMOS) |
|  | VH | 0.5 | V | Transition voltage (for enhanced NMOS) |
|  |  | -0.5 | V | Transition voltage (for enhanced PMOS) |
| 3 | RON | $1.0 \times 10^{3}$ | $\Omega$ | "On" resistance |
| 4 | CREC | 0 | F | Total overlap capacitance |
| 5 | C 1 | $10 \times 10^{-15}$ | F | Switch input capacitance |
| 6 | C 2 | $10 \times 10^{-15}$ | F | Switch output capacitance |

## Further Explanation of Parameters

- VTH

Threshold voltage. The voltage at which the "off" resistance starts changing.

- VH

When the control voltage $\mathrm{V}(\mathrm{NC})$ reaches $\mathrm{V}+\mathrm{H}+\mathrm{VH}$, the switch attains the "on" resistance.

## Example

```
.model styp nsw vh=0.4 vth=0.5 ron=1k crec= 50f
...
s7 ck3 5 7 styp
```

Specifies the switch s7 of model type styp (N-type) placed between the nodes 5 and 7 with controlling node ck3. The electrical parameters of the switch are specified using the .MODEL command.

## Z-domain Representation

## General Notes on the Use of Macromodels

The following macromodels are basic building blocks for switched capacitor filters and sampled data systems, controlled by two clock phases 1 and 2. The behavior of each SC element is characterized by an admittance matrix which is created internally during the transient or the AC analysis as a function of the parameters (capacitance c, period TP of the controlling clocks and the LDI flag). This matrix transforms the vector of all the pin voltages into the vector of all the currents entering the pins of the element. This transformation works in a (discrete) time domain as well as in a frequency domain and allows both the transient and AC analyses of the SC circuit.

## Note

The controlling clock signals are represented by the parameter тP.

This modeling approach is linear, but extremely fast. Using this approach, a transient analysis can be performed within a few seconds, whereas a couple of hours would be required if the SC filter was built on a transistor circuit description level!

The following section illustrates the uses of these macromodels.
LDI Definition: LDI Transformation flag can equal 0,1 or 2 . It is only important for AC analysis. It has to be set if a switched capacitor representation of a resistor is connected to the inverting input of an op-amp, with a feedback capacitance and if both form an LDI, LDI=1 or 2 identifies the switch branch, which is connected to the inverting input of the op-amp by its equally named controlling clock-phase.

See "SC Integrators \& LDI's" on page 493.

The effect is that the current of the corresponding switch branch will be delayed by a factor of $z-1 / 2$. If LDI=0, no LDI transformation will be performed.

## Ideal Operational Amplifier

Yxx SC_IDEAL [PIN:] INP INN OUT [PARAM: M=val]
Figure 9-10. Ideal Operational Amplifier Macromodel


This is an ideal operational amplifier macromodel implemented for use as a basic building block in SC circuits and sampled data systems.

## Model Pins

- INP

Non-inverting input

- INN

Inverting input

- OUT

Output

- PARAM: M=VAL

Device multiplier. Simulates the effect of multiple devices in parallel. In effect the current value is multiplied by m. Default is 1 . . option ymfact must be selected in order for this option to work.

Note $\qquad$
A feedback connection between output and input is recommended.

## SC Integrators \& LDI's

One of the most important applications of Z-domain SC elements is in the construction of SC Integrators \& LDI's, the key elements for the design of switch capacitor filters and sampled data systems. In these applications they are basic building blocks, along with others such as delay elements, sample-and-hold elements, summing amplifiers etc.

But even the SC Integrators can be further decomposed into more elementary basic building blocks, namely SC resistors (sc_i, sc_n, sc_p, and so on), op-amps (sc_ideal, opa) and unswitched capacitors (sc_u). Most SC Integrators represent the same RC Integrator. They have approximately the same transfer function if the resistor R1 is substituted by an appropriate switched capacitor (sc_i, sc_n, sc_p, and so on). See the figure below:

Figure 9-11. SC Integrators \& LDI's



## Note

The transfer function of an SC Integrator depends on the sampling instants of the output signal, i.e. different clock phases $\boldsymbol{k}$, which control the switch path at the output of the integrator causing different transfer functions of this integrator.

This is now explained exactly in the formal mathematical language.
Supposing that:
$\boldsymbol{i}$ is the phase which controls the switch branch at the input of the integrator,
$\boldsymbol{j}$ is the phase which controls the switch branch at the inverting input of the op-amp,
$\boldsymbol{k}$ is the phase which controls the switch branch at the output of the integrator, and $\boldsymbol{H}_{i j \boldsymbol{k}}$ is the transfer function of the integrator controlled by $\boldsymbol{i}, \boldsymbol{j}, \boldsymbol{k}$.
The following relationship will be true:

$$
H_{i j k}(z)=H_{i k k}(z) \times z^{\alpha}
$$

where $\boldsymbol{H}_{i j \boldsymbol{k}}(z)$ and $\boldsymbol{H}_{i \boldsymbol{k} \boldsymbol{k}}(z)$ are the transfer functions corresponding to the same type $\boldsymbol{H}$ of the integrator but controlled by the clock phases $\boldsymbol{i}, \boldsymbol{j}, \boldsymbol{k}$ and $\boldsymbol{i}, \boldsymbol{k}, \boldsymbol{k}$ respectively and:

$$
\alpha=\left\{\begin{array}{l}
0 \text { if } j=k \\
o r \\
-0.5 \text { otherwise }
\end{array}\right.
$$

that is:

$$
L D I=\left\{\begin{array}{l}
0 \text { if } j=k \\
o r \\
j \text { otherwise }
\end{array}\right.
$$

This information is taken from:
Rolf Unbehauen, Andrzej Cichocki, "MOS Switched Capacitor and Continuous-Time Integrated Circuits and Systems."

For examples, please see "Applications" on page 512.

## Inverting Switched Capacitor

```
Yxx SC_I [PIN:] P1 P2 N2 N1 [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 9-12. Inverting Switched Capacitor Macromodel


This is a basic building block for Z-domain modeling of SC circuits and sampled data systems. It represents an SC realization of an analog resistor, the so called inverting switched capacitor.

It has been modeled as a voltage to current four port transfer element with a characteristic transfer or admittance matrix $\mathrm{Y}(\mathrm{z})$, used for the description of the behavior of this element for both the transient and small signal AC analyses. The transfer function can be symbolically represented as shown above.

It is a Kirchhoff type element having a time-discrete I-U-dependence with charge storage and delay effects controlled by the uniform two-phase clock.

The model assumes that all currents remain constant during each switching phase and that they only change their values at the beginning of every switching sub-interval.

Only one sc_i model should be connected to an amplifier summing node (minus input). Simulation results will be incorrect if two or more sc_i macromodels are connected to the minus input node of an amplifier. In this particular case, current (charge) from output nodes of the sc_i macro is not summed together in the correct way.

## Model Pins

- P1

Name of the positive pin to the switch branch controlled by clock phase 1

- P2

Name of the positive pin to the switch branch controlled by clock phase 2

- N 1

Name of the negative pin to the switch branch controlled by clock phase 1

- N 2

Name of the negative pin to the switch branch controlled by clock phase 2

Table 9-3. Inverting Switched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C | $1.0 \times 10^{-12}$ | F | Capacitance |
| 2 | TP | $1.0 \times 10^{-6}$ | s | Pulse period |
| 3 | LDI | 0 |  | See the note on LDI's in this chapter |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

## Note

The above macromodel parameters can be declared in a number of ways, listed below in order of priority.

1. In the instantiation line, using the . Param keyword.
2. In a model command line. The syntax is as follows:
.model mname modfas par=val [par=val]
If this syntax is used, a model name must be declared using the .model keyword in the instantiation line.
3. If no parameters are explicitly declared, the parameter default values are used.

## Model Equations

This element performs the linear Z-domain transfer function:

$$
\left[\mathrm{I}_{\mathrm{p} 1}(\mathrm{z}), \mathrm{I}_{\mathrm{n} 1}(\mathrm{z}), \mathrm{I}_{\mathrm{p} 2}(\mathrm{z}), \mathrm{I}_{\mathrm{n} 2}(\mathrm{z})\right]=\mathrm{Y}(\mathrm{z}, \mathrm{LDI})\left[\mathrm{V}_{\mathrm{p} 1}(\mathrm{z}), \mathrm{V}_{\mathrm{n} 1}(\mathrm{z}), \mathrm{V}_{\mathrm{p} 2}(\mathrm{z}), \mathrm{V}_{\mathrm{n} 2}(\mathrm{z})\right]
$$

in the time and frequency domain for the transient and small signal AC analyses where:
$\mathrm{I}_{\mathrm{p} 1}, \mathrm{I}_{\mathrm{n} 1}, \mathrm{I}_{\mathrm{p} 2}, \mathrm{I}_{\mathrm{n} 2}$ are the currents contributed to the pins P1, N1, P2, N2.
$\mathrm{V}_{\mathrm{p} 1}, \mathrm{~V}_{\mathrm{n} 1}, \mathrm{~V}_{\mathrm{p} 2}, \mathrm{~V}_{\mathrm{n} 2}$ are the voltages at the nodes $\mathrm{P} 1, \mathrm{~N} 1, \mathrm{P} 2, \mathrm{~N} 2$.
$\mathrm{Y}(\mathrm{z}, \mathrm{LDI})$ is the characteristic transfer or admittance matrix of the model.
The Z-transfer matrix $\boldsymbol{Y}(\boldsymbol{z}, \mathbf{0})$ is the Z-transform of the difference equations describing the time domain behavior of this element. Therefore the case of $\operatorname{LDI}=0$ is completely adequate to the time domain behavior.

In some SC Integrators, the pins P2, N1 are grounded, whereas N2 is connected to the virtual ground of an ideal op-amp, in which case the transfer function at node N 2 becomes the following form:

$$
I_{n 2}(z)=\frac{C}{T p} \times z^{-1 / 2} \times V_{p 1}(z)
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

## Non-inverting Switched Capacitor

Yxx SC_N [PIN:] P1 P2 N1 N2 [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 9-13. Non-inverting Switched Capacitor Macromodel


This is a basic building block for Z-domain modeling of SC circuits and sampled data systems. It represents an SC realization of an analog resistor, the so called non-inverting switched capacitor.

It has been modeled as a voltage to current four port transfer element with a characteristic transfer or admittance matrix $\mathrm{Y}(\mathrm{z})$, used for the description of the behavior of this element for both the transient and small signal AC analyses. The transfer function can be symbolically represented as shown above.

It is a Kirchhoff type element having a time-discrete I-U-dependence with charge storage and delay effects controlled by the uniform two-phase clock.

The model assumes that all currents remain constant during each switching phase and that they only change their values at the beginning of every switching sub-interval.

## Model Pins

- P1

Name of the positive pin to the switch branch controlled by clock phase 1

- P2

Name of the positive pin to the switch branch controlled by clock phase 2

- N 1

Name of the negative pin to the switch branch controlled by clock phase 1

- N 2

Name of the negative pin to the switch branch controlled by clock phase 2

Table 9-4. Non-inverting Switched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C | $1.0 \times 10^{-12}$ | F | Capacitance |

Table 9-4. Non-inverting Switched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 2 | TP | $1.0 \times 10^{6}$ | s | Pulse period |
| 3 | LDI | 0 |  | See the note on LDI's in this chapter |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

## Note

The above macromodel parameters can be declared in a number of ways, listed below in order of priority.

1. In the instantiation line, using the . Param keyword.
2. In a model command line. The syntax is as follows:
```
.model mname modfas par=val [par=val]
```

If this syntax is used, a model name must be declared using the .model keyword in the instantiation line.
3. If no parameters are explicitly declared, the parameter default values are used.

## Model Equations

This element performs the linear Z-domain transfer function:

$$
\left[\mathrm{I}_{\mathrm{p} 1}(\mathrm{z}), \mathrm{I}_{\mathrm{n} 1}(\mathrm{z}), \mathrm{I}_{\mathrm{p} 2}(\mathrm{z}), \mathrm{I}_{\mathrm{n} 2}(\mathrm{z})\right]=\mathrm{Y}(\mathrm{z}, \mathrm{LDI})\left[\mathrm{V}_{\mathrm{p} 1}(\mathrm{z}), \mathrm{V}_{\mathrm{n} 1}(\mathrm{z}), \mathrm{V}_{\mathrm{p} 2}(\mathrm{z}), \mathrm{V}_{\mathrm{n} 2}(\mathrm{z})\right]
$$

in the time and frequency domain for the transient and small signal AC analyses where:
$\mathrm{I}_{\mathrm{p} 1}, \mathrm{I}_{\mathrm{n} 1}, \mathrm{I}_{\mathrm{p} 2}, \mathrm{I}_{\mathrm{n} 2}$ are the currents contributed to the pins P1, N1, P2, N2.
$\mathrm{V}_{\mathrm{p} 1}, \mathrm{~V}_{\mathrm{n} 1}, \mathrm{~V}_{\mathrm{p} 2}, \mathrm{~V}_{\mathrm{n} 2}$ are the voltages at the nodes $\mathrm{P} 1, \mathrm{~N} 1, \mathrm{P} 2, \mathrm{~N} 2$.
$\mathrm{Y}(\mathrm{z}, \mathrm{LDI})$ is the characteristic transfer or admittance matrix of the model.
The Z-transfer matrix $\boldsymbol{Y}(\boldsymbol{z}, \mathbf{0})$ is the Z-transform of the difference equations describing the time domain behavior of this element. Therefore the case of $\operatorname{LDI}=0$ is completely adequate to the time domain behavior.

In some SC Integrators the pins P2, N2 are grounded whereas N1 is connected to the virtual ground of an ideal op-amp, in which case the transfer function at node N 1 becomes the following form:

$$
I_{n 1}(z)=-\frac{C}{T p} \times V_{p 1}(z)
$$

where:

Switched Capacitor Macromodels
Non-inverting Switched Capacitor

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

## Parallel Switched Capacitor

Yxx SC_P [PIN:] P1 P2 N [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 9-14. Parallel Switched Capacitor Macromodel CLOCK


This is a basic building block for Z-domain modeling of SC circuits and sampled data systems. It represents an SC realization of an analog resistor, the so called parallel switched capacitor.

It has been modeled as a voltage to current three port transfer element with a characteristic transfer or admittance matrix $\mathrm{Y}(\mathrm{z})$, used for the description of the behavior of this element for both the transient and small signal AC analyses. The transfer function can be symbolically represented as shown above.

It is a Kirchhoff type element having a time-discrete I-U-dependence with charge storage and delay effects controlled by the uniform two-phase clock.

The model assumes that all currents remain constant during each switching phase and that they only change their values at the beginning of every switching sub-interval.

## Model Pins

- P1

Name of the positive pin to the switch branch controlled by clock phase 1

- P2

Name of the positive pin to the switch branch controlled by clock phase 2

- N

Name of the negative pin at the outer side of the capacitor not connected to the switches of this element

Table 9-5. Parallel Switched Capacitor

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C | $1.0 \times 10^{-12}$ | F | Capacitance |
| 2 | TP | $1.0 \times 10^{6}$ | s | Pulse period |
| 3 | LDI | 0 |  | See the note on LDI's in this chapter |

Table 9-5. Parallel Switched Capacitor

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

Note $\qquad$
The above macromodel parameters can be declared in a number of ways, listed below in order of priority.

1. In the instantiation line, using the . Param keyword.
2. In a model command line. The syntax is as follows:
```
.model mname modfas par=val [par=val]
```

If this syntax is used, a model name must be declared using the .model keyword in the instantiation line.
3. If no parameters are explicitly declared, the parameter default values are used.

## Model Equations

This element performs the linear Z-domain transfer function:

$$
\left[I_{p 1}(z), I_{p 2}(z), I_{n}(z)\right]=Y(z, L D I)\left[V_{p 1}(z), V_{p 2}(z), V_{n}(z)\right]
$$

in the time and frequency domain for the transient and small signal AC analyses where:
$\mathrm{I}_{\mathrm{p} 1}, \mathrm{I}_{\mathrm{p} 2}, \mathrm{I}_{\mathrm{n}}$ are the currents contributed to the pins P1, P2, N.
$\mathrm{V}_{\mathrm{p} 1}, \mathrm{~V}_{\mathrm{p} 2}, \mathrm{~V}_{\mathrm{n}}$ are the voltages at the nodes $\mathrm{P} 1, \mathrm{P} 2, \mathrm{~N}$.
$\mathrm{Y}(\mathrm{z}, \mathrm{LDI})$ is the characteristic transfer or admittance matrix of the model.
The Z-transfer matrix $\boldsymbol{Y}(\boldsymbol{z}, \mathbf{0})$ is the Z-transform of the difference equations describing the time domain behavior of this element. Therefore the case of $\operatorname{LDI}=0$ is completely adequate to the time domain behavior.

In some SC Integrators the pin N is grounded whereas P 2 is connected to the virtual ground of an ideal op-amp, in which case the transfer function becomes the following form:

$$
I_{p 2}(z)=-\frac{C}{T p} \times z^{-1 / 2} \times V_{p 1}(z)
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

## Serial Switched Capacitor

```
Yxx SC_S1 [PIN:] IN OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
Yxx SC_S2 [PIN:] IN OUT [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
```

Figure 9-15. Serial Switched Capacitor

SC_S 1


SC_S2
IN


These are basic building blocks for the Z-domain modeling of SC circuits and sampled data systems. They represent SC realizations of an analog resistor, the so called serial switched capacitor.

They have been modeled as voltage to current two port transfer elements with a characteristic transfer or admittance matrix $\mathrm{Y}(\mathrm{z})$, used for the description of the behavior of these elements for both the transient and small signal AC analyses. The transfer function can be symbolically represented as shown above.

They are Kirchhoff type elements having a time-discrete I-U-dependence with charge storage and delay effects controlled by the uniform two-phase clock.

The model assumes, that all currents remain constant during each switching phase and that they only change their values at the beginning of every switching sub-interval.

## Model Pins

- IN

Name of the positive pin to the switch branch controlled by clock phase 1 (or 2)

- OUT

Name of the pin to the switch branch controlled by clock phase 2 (or 1)

Table 9-6. Serial Switched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C | $1.0 \times 10^{-12}$ | F | Capacitance |
| 2 | TP | $1.0 \times 10^{6}$ | s | Pulse period |

Table 9-6. Serial Switched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 3 | LDI | 0 |  | See the note on LDI's in this chapter |
| 4 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

## Note

The above macromodel parameters can be declared in a number of ways, listed below in order of priority.

1. In the instantiation line, using the . PARAM keyword.
2. In a model command line. The syntax is as follows:
.model mname modfas par=val [par=val]
If this syntax is used, a model name must be declared using the .model keyword in the instantiation line.
3. If no parameters are explicitly declared, the parameter default values are used.

## Model Equations

This element performs the linear Z-domain transfer function:

$$
\left[I_{\text {in }}(z), I_{\text {out }}(z)\right]=Y(z, L D I)\left[V_{\text {in }}(z), V_{\text {out }}(z)\right]
$$

in the time and frequency domain for the transient and small signal AC analyses where:
$\mathrm{I}_{\mathrm{in}}, \mathrm{I}_{\text {out }}$ are the currents contributed to the pins IN, OUT.
$\mathrm{V}_{\mathrm{in}}, \mathrm{V}_{\text {out }}$ are the voltages at the nodes IN, OUT.
$\mathrm{Y}(\mathrm{z}$, LDI) is the characteristic transfer or admittance matrix of the model.
The Z-transfer matrix $\boldsymbol{Y}(\boldsymbol{z}, \mathbf{0})$ is the Z-transform of the difference equations describing the time domain behavior of this element. Therefore the case of LDI=0 is completely adequate to the time domain behavior.

In some SC Integrators the pin out is connected to the virtual ground of an ideal op-amp, in which case the transfer function becomes the following form:

$$
I_{\text {out }}(z)=-\frac{C}{T p} \times V_{i n}(z)
$$

where: $z^{k}=e^{j \omega(k \times T p)}, k \in$ Integer

## Serial-parallel Switched Capacitor

```
Yxx SC_SP1 [PIN:] IN OUT REF [PARAM: PAR=VAL {PAR=VAL}] [MODEL: MNAME]
YXx SC_SP2 [PIN:] IN OUT REF [PARAM: PAR=VAL {PAR=VAL}][MODEL: MNAME]
```

Figure 9-16. Serial-parallel Switched Capacitor Macromodel

SC_SP2


These are basic building blocks for the Z-domain modeling of SC circuits and sampled data systems. They represent SC realizations of an analog resistor, the so called serial-parallel switched capacitor.

They have been modeled as voltage to current three port transfer elements with a characteristic transfer or admittance matrix $\mathrm{Y}(\mathrm{z})$, used for the description of the behavior of these elements for both the transient and small signal AC analyses. The transfer function can be symbolically represented as shown above.

They are Kirchhoff type elements having a time-discrete I-U-dependence with charge storage and delay effects controlled by the uniform two-phase clock.

The model assumes, that all currents remain constant during each switching phase and that they only change their values at the beginning of every switching sub-interval.

## Model Pins

- IN

Name of the positive pin to the switch branch controlled by clock phase 1 (or 2)

- out

Name of the positive pin to the switch branch controlled by clock phase 2 (or 1)

- REF

Name of the negative pin

Table 9-7. Serial-parallel Switched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C 1 | $1.0 \times 10^{-12}$ | F | Capacitance |
| 2 | C 2 | $1.0 \times 10^{-12}$ | F | Capacitance |
| 3 | TP | $1.0 \times 10^{6}$ | s | Pulse period |
| 4 | LDI | 0 |  | See the note on LDI's in this chapter |
| 5 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. OPTION YMFACT must be specified for $\mathbf{M}$ to work.

## Note

$\qquad$
The above macromodel parameters can be declared in a number of ways, listed below in order of priority.

1. In the instantiation line, using the . PARAM keyword.
2. In a model command line. The syntax is as follows:
.model mname modfas par=val [par=val]
If this syntax is used, a model name must be declared using the .model keyword in the instantiation line.
3. If no parameters are explicitly declared, the parameter default values are used.

## Model Equations

These elements perform the linear Z-domain transfer function:

$$
\left[I_{i n}(z), I_{\text {out }}(z), I_{r e f}(z)\right]=Y(z, L D I)\left[V_{\text {in }}(z), V_{\text {out }}(z), V_{r e f}(z)\right]
$$

in the time and frequency domain for the transient and small signal AC analyses where:
$\mathrm{I}_{\mathrm{in}}, \mathrm{I}_{\mathrm{out}}, \mathrm{I}_{\text {ref }}$ are the currents contributed to the pins IN, OUT, REF.
$\mathrm{V}_{\mathrm{in}}, \mathrm{V}_{\text {out }}, \mathrm{V}_{\text {ref }}$ are the voltages at the nodes IN, OUT, REF.
$\mathrm{Y}(\mathrm{z}, \mathrm{LDI})$ is the characteristic transfer or admittance matrix of the model.
The Z-transfer matrix $\boldsymbol{Y}(\boldsymbol{z}, \mathbf{0})$ is the Z-transform of the difference equations describing the time domain behavior of this element. Therefore the case of LDI=0 is completely adequate to the time domain behavior.

In some SC Integrators the pin N is connected to the virtual ground of an ideal op-amp, in which case the transfer function becomes the following form:

$$
I_{\text {out }}(z)=-\frac{1}{T p}\left(C_{1}+C_{2} z^{-1 / 2}\right) \times V_{i n}
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

## Bi-linear Switched Capacitor

Yxx SC_B [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 9-17. Bi-linear Switched Capacitor Macromodel


CLOCK


This is a basic building block for Z-domain modeling of SC circuits and sampled data systems. It represents an SC realization of an analog resistor, the so called bi-linear switched capacitor.

It has been modeled as a voltage to current two port transfer element with a characteristic transfer or admittance matrix $\mathrm{Y}(\mathrm{z})$, used for the description of the behavior of this element for both the transient and small signal AC analyses. The transfer function can be symbolically represented as shown in the above diagram.

It is a Kirchhoff type element having a time-discrete I-U-dependence with charge storage and delay effects controlled by the uniform two-phase clock.

The model assumes that all currents remain constant during each switching phase and that they only change their values at the beginning of every switching sub-interval.

## Model Pins

- IN

Name of the first pin

- OUT

Name of the second pin

Table 9-8. Bi-linear Switched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C | $1.0 \times 10^{-12}$ | F | Capacitance |
| 2 | TP | $1.0 \times 10^{6}$ | s | Pulse period |
| 3 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

## Note

The above macromodel parameters can be declared in a number of ways, listed below in order of priority.

1. In the instantiation line, using the . PARAM keyword.
2. In a model command line. The syntax is as follows:
.model mname modfas par=val [par=val]
If this syntax is used, a model name must be declared using the .model keyword in the instantiation line.
3. If no parameters are explicitly declared, the parameter default values are used.

## Model Equations

This element performs the linear Z-domain transfer function:

$$
\left[I_{\text {in }}(z), I_{\text {out }}(z)\right]=Y(z, L D I)\left[V_{\text {in }}(z), V_{\text {out }}(z)\right]
$$

in the time and frequency domains for the transient and small signal AC analyses where:
$\mathrm{I}_{\mathrm{in}}, \mathrm{I}_{\text {out }}$ are the currents contributed to the pins IN, OUT.
$\mathrm{V}_{\mathrm{in}}, \mathrm{V}_{\text {out }}$ are the voltages at the nodes IN, OUT.
$\mathrm{Y}(\mathrm{z}, \mathrm{LDI})$ is the characteristic transfer or admittance matrix of the model.
In some SC Integrators, the pin out is connected to the virtual ground of an ideal op-amp, in which case the transfer function becomes the following form:

$$
I_{o u t}(z)=-\frac{C}{T p} \times\left(1+z^{-1}\right) \times V_{i n}(z)
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

## Unswitched Capacitor

Yxx SC_U [PIN:] IN OUT [PARAM: PAR=VAL \{PAR=VAL\}] [MODEL: MNAME]
Figure 9-18. Unswitched Capacitor Macromodel



This is a basic building block for Z-domain modeling of SC circuits and sampled data systems. It represents an SC realization of an unswitched capacitor.

It is a Kirchhoff type element having a time-discrete I-U-dependence with charge storage and delay effects controlled by the uniform two-phase clock.

The model assumes that all currents remain constant during each switching phase and that they only change their values at the beginning of every switching sub-interval.

## Model Pins

- IN

Name of the input pin

- OUT

Name of the output pin

Table 9-9. Unswitched Capacitor Model Parameters

| Nr. | Name | Default | Units | Definition |
| :--- | :--- | :--- | :--- | :--- |
| 1 | C | $1.0 \times 10^{-12}$ | F | Capacitance |
| 2 | TP | $1.0 \times 10^{6}$ | s | Pulse period |
| 3 | $\mathrm{M}^{1}$ | 1 |  | Device multiplier |

1. . OPTION YMFACT must be specified for $\mathbf{M}$ to work.

The above macromodel parameters can be declared in a number of ways, listed below in order of priority:

1. In the instantiation line, using the . PARAM keyword.
2. In a model command line. The syntax is as follows:
```
.model mname modfas par=val [par=val]
```

If this syntax is used, a model name must be declared using the .model keyword in the instantiation line.
3. If no parameters are explicitly declared, the parameter default values are used.

## Model Equations

This element performs the linear Z-domain transfer function:

$$
\left[I_{\text {in }}(z), I_{\text {out }}(z)\right]=Y(z)\left[V_{\text {in }}(z), V_{\text {out }}(z)\right]
$$

in the time and frequency domains for the transient and small signal AC analyses where:
$\mathrm{I}_{\mathrm{in}}, \mathrm{I}_{\text {out }}$ are the currents contributed to the pins IN, OUT.
$\mathrm{V}_{\mathrm{in}}, \mathrm{V}_{\text {out }}$ are the voltages at the nodes IN, OUT.
$\mathrm{Y}(\mathrm{z})$ is the characteristic transfer or admittance matrix of the model.
The Z-transfer matrix $\boldsymbol{Y}(\boldsymbol{z})$ is the Z-transform of the difference equations describing the time domain behavior of this element.

## Applications

The list below gives some of the applications of Switched Capacitor Macromodels which are illustrated throughout the following pages.

- Non-inverting Integrator
- LDI Phase Control Non-inverting Integrator
- Euler Forward Integrator
- LDI Phase Control Euler Forward Integrator
- Euler Backward Integrator
- LDI Phase Control Euler Backward Integrator


## Non-inverting Integrator

Figure 9-19. Non-inverting Integrator


The inverting switched capacitor is connected to the input of an op-amp with a feedback capacitor forming a non-inverting Integrator. In this configuration, both the input and output nodes of the op-amp are controlled by the same clock phase, namely clock phase 2 , as shown above.

This is the standard use of the switched capacitor element and therefore LDI=0, which means that no additional delay operation has to be performed during an AC analysis.

This leads to the Z-domain transfer function:

$$
\operatorname{vout}(z)=\frac{C}{C F} \times \frac{z^{-1 / 2}}{1-z^{-1}} \times \operatorname{vin}(z)
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

which describes the behavior in the time and frequency domain for the transient and small signal AC analyses.

## LDI Phase Control Non-inverting Integrator

Figure 9-20. LDI Phase Control Non-inverting Integrator Macromodel


Here, the inverting switched capacitor is connected to the inverting input of an op-amp with a feedback capacitor forming a non-inverting Integrator. In this configuration the inverting input node and the output node of the op-amp are controlled by different clock phases.

This is the non-standard use of the switched capacitor element and therefore the LDI flag has to be set properly, which means that during an AC analysis, a delay operation of one half clock period has to be applied to the current through the switch branch of the SC element, which is connected to the input of the op-amp.

The LDI flag identifies this switch branch by the name (the number 1 or 2 ) of the clock phase, through which it is controlled. So LDI=2 in the case of the above arrangement.

This leads to the transfer function:

$$
\operatorname{vout}(z)=\frac{C}{C F} \times \frac{z^{-1}}{1-z^{-1}} \times \operatorname{vin}(z)
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

which describes the behavior in the time and frequency domain for the transient and small signal AC analyses.

## Euler Forward Integrator

Figure 9-21. Euler Forward Integrator Macromodel


Transfer Function

$$
\operatorname{vout}(z)=-\frac{C}{C F} \times \frac{z^{-1 / 2}}{1-z^{-1}} \times \operatorname{vin}(z)
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

## LDI Phase Control Euler Forward Integrator

Figure 9-22. LDI Phase Control Euler Forward Integrator Macromodel


Transfer Function

$$
\operatorname{vout}(z)=-\frac{C}{C F} \times \frac{z^{-1}}{1-z^{-1}} \times \operatorname{vin}(z)
$$

where:

$$
z^{k}=e^{j \omega\left(k \times T_{p}\right)}, k \in \text { Integer }
$$

## Euler Backward Integrator

Figure 9-23. Euler Backward Integrator Macromodel


Transfer Function

$$
\operatorname{vout}(z)=-\frac{C}{C F} \times \frac{1}{1-z^{-1}} \times \operatorname{vin}(z)
$$

where:

$$
z^{k}=e^{j \omega(k \times T p)}, k \in \text { Integer }
$$

## LDI Phase Control Euler Backward Integrator

Figure 9-24. LDI Phase Control Euler Backward Integrator Macromodel


How to deduct the transfer function of an SC Integrator with:

- The transfer function of the SC resistor:

$$
Y_{n s c}(z)=C \times v i n(z) \times d e l_{L D I}
$$

- The LDI-delay:

$$
\operatorname{del}_{L D I}=z^{-1 / 2}
$$

- The transfer function of the unswitched capacitor in the feedback loop:

$$
Y_{u s c}(z)=C_{F} \times\left(1-z^{-1}\right)
$$

- The KCL at the virtual ground node:

$$
Y_{i s c}(z) \times V_{i n}(z)+Y_{u s c}(z) \times V_{\text {out }}(z)=0
$$

We get the transfer function of the integrator as follows:

$$
V_{o u t}(z)=-\frac{C}{C F} \times \frac{z^{-1 / 2}}{1-z^{-1}} \times V_{i n}(z)
$$

## Tutorial-SC Low Pass Filter

For a tutorial on the transient and small signal AC analysis of an SC low pass filter using the Zdomain switched capacitor models, please see "Tutorial \#9—SC Low Pass Filter" on page 1369.

## Chapter 10 Simulator Commands

## Command Summary

In the following summary tables, commands have been organized into four groups according to their function.

- Analysis Commands
- Display Commands
- Simulation Control Commands
- Circuit Description Commands

In each of the command summary tables you can click on a command name to jump to its detailed description. The detailed command descriptions are listed in alphabetical order later in this chapter, see "Command Descriptions" on page 527.

## Analysis Commands

Use these commands to instruct Eldo to perform a specific analysis.
Table 10-1. Eldo Analysis Commands

| Command | Description |
| :--- | :--- |
| . AC | Activates the small signal analysis which computes the magnitude and <br> phase of output variables as a function of frequency |
| . AGE | Activates the Age analysis to test the reliability of a netlist |
| .CHECKSOA | Causes Eldo to check for any violations of the circuit safe operating <br> area (SOA) limits specified via the .SETSOA command |
| .DC | Activates a DC analysis, and is used to determine the quiescent state or <br> operating point of the circuit |
| . DCHIZ | Detects high impedance values for DC analysis |
| . DCMISMATCH | Computes the sensitivity of node voltages and of currents through <br> voltage sources |
| . DEX | Design of Experiments. Used to perform factor screening before <br> attempting to solve subsequent statistical problems. |
| . DSP | Selects the waveform on which you require DSP to be applied |

Table 10-1. Eldo Analysis Commands

| Command | Description |
| :---: | :---: |
| .DSPMOD | Defines a set of parameters for a PSD computation using the correlogram or periodogram method. Generates a histogram of the input wave showing the wave's magnitude probability density distribution. Provides access to the EZwave frequency measurement. |
| .FOUR | Selects the waveform on which the user requires FFT to be done |
| .LSTB | Improves the analysis of circuit stability |
| .MC | Performs a Monte Carlo analysis |
| .NOISE | Controls the noise analysis of the circuit and must be used in conjunction with an AC analysis |
| .NOISETRAN | Controls the transient noise analysis of a circuit and must be used in conjunction with a transient (.TRAN) analysis |
| . OP | Forces Eldo to determine the DC operating point of the circuit with inductors short-circuited and capacitors opened |
| .OPTFOUR | Used to supply the options for the FFT post-processor |
| .OPTIMIZE | Specifies an optimization configuration acting on all the analyses specified in the circuit netlist |
| .OPTNOISE | Allows more flexibility in the output of the AC noise analysis results |
| .PZ | For Pole-Zero analysis |
| .RAMP | Use when Eldo encounters difficulties finding a DC operating point with the conventional .DC command |
| .SENS | Causes a DC sensitivity analysis to be performed |
| .SENSAC | Causes an AC sensitivity analysis to be performed |
| .SENSPARAM | Activates a sensitivity analysis of extracts versus subcircuit parameters |
| .SNF | Calculates a Spot Noise Figure |
| .SOLVE | Solves the value of a parameter |
| .TF | Causes the small signal Transfer Function to be calculated by linearizing around a bias point |
| .TRAN | Activates a transient analysis |
| .WCASE | Computes worst case values for waveform data extracted using the .EXTRACT command according to a set of parameters that have LOT and DEV variations |

## Display Commands

Use these commands to control the messages and outputs generated from simulation.
Table 10-2. Eldo Display Commands

| Command | Description |
| :---: | :---: |
| .COMCHAR | Changes the comment character on an input file |
| .DEFMAC | Defines a parameterized macro which may be instantiated in the circuit netlist |
| .DEFPLOTDIG | Enables you to plot an analog signal as a digital bus |
| .DEFWAVE | Defines a new waveform by relating previously defined waveforms and nodes |
| .EQUIV | Changes the name of a netlist node to a new display name |
| .EXTMOD | Performs only the .EXTRACT commands, without performing the simulation(s) |
| .EXTRACT | Extracts waveform information using a combination of arithmetic expressions or pre-defined functions |
| .FFILE | S, Y, Z Parameter output file specification |
| .IPROBE | Probes current between pins |
| .MEAS | An alternative to the .EXTRACT command |
| .MONITOR | Displays the steps taken by the simulator when doing an AC, TRAN or DCSWEEP simulation |
| .NET | Extracts the $\mathrm{S}, \mathrm{Y}, \mathrm{Z}$ or H parameters in the frequency domain for a specified circuit |
| .NEWPAGE | Allows the control of the saved windows file in the EZwave waveform viewer |
| .NOCOM | Suppresses any comment lines in the ASCII output (.chi) file which come after it in the netlist |
| .NOTRC | Suppresses the rewriting of the circuit description file in the ASCII output (.chi) file |
| .OBJECTIVE | Based on the .EXTRACT construct, and specifically dedicated to optimization |
| .OP_DISPLAY | DC operating point display. Enables the printing of alternative voltage threshold (VT) for MOS devices. Used in conjunction with a .op command. |
| .PLOT | Specifies which simulation results have to be kept by the simulator for graphical viewing and post-processing |
| .PLOTBUS | Plots all the bits of a bus |

Table 10-2. Eldo Display Commands

| Command | Description |
| :--- | :--- |
| . PRINT | Defines the contents of a tabular listing of any number of output <br> variables. Results are written to the .chi file in ASCII. |
| . PRINTBUS | Prints all the bits of a bus |
| . PRINTFILE | Defines the contents of a tabular listing of any number of output <br> variables, and dumps them to the specified file in ASCII format or as a <br> .DATA statement |
| . PROBE | Defines the contents of a tabular listing of any number of output <br> variables. Results are written to.$w d b$ binary output files for post- <br> processing. |
| . PROBEBUS | Plots all the bits of a bus |
| . WIDTH | Sets the paper width of the output print device |

## Simulation Control Commands

Use these commands to modify general options for simulation.
Table 10-3. Eldo Simulation Control Commands

| Command | Description |
| :--- | :--- |
| .CALL_TCL | Performs a single call to a Tcl function |
| .CHECKBUS | Checks for a specified value of the bus at a specified time |
| .CONSO | Computes and displays the average current flowing through the specified <br> voltage source(s) during the simulation period |
| .CORREL | Specifies correlations between parameters during a Monte Carlo analysis |
| .DATA | Performs a parameter sweep |
| .DISCARD | Specifies whether one or more subcircuits, instances or devices should be <br> ignored during an Eldo simulation |
| .DISFLAT | Disables the flat netlist mode |
| .DISTRIB | Specifies user-defined distributions for the device tolerances DEV and <br> LOT used in Monte Carlo analysis |
| .FFILE | Specifies S, Y, Z parameter output file |
| .FILTER | Provides filtering capability for simulations, extractions, or to create <br> subsets of .DATA statements |
| .FORCE | Forces one or more nodes to specified voltage(s) with respect to ground <br> for the initial transient solution |
| .FUNC | Defines functions used in expressions |

Table 10-3. Eldo Simulation Control Commands

| Command | Description |
| :--- | :--- |
| .GUESS | Aids the calculation of the DC operating point by setting voltage values <br> at selected nodes for the first iteration of a DC operating point calculation |
| .IC | Fixes node voltages for the duration of a DC analysis |
| .INIT | Initializes digital circuits |
| .LOAD | Takes a set of previously saved voltages and inserts these as .NODESET, <br> .GUESS or .IC commands |
| .LOTGROUP | Allows different entities to share the same distribution |
| .MCMOD | Specifies the amount of variation on a given model parameter using the <br> LOT and/or DEV parameters. Used in combination with Monte Carlo and <br> Worst Case analyses. |
| .MODDUP | Tells Eldo that for each device_name a private .MODEL command be <br> created. Useful in connection with SimPilot/Aspire only |
| .MPRUN | Runs multiple simulations on one multi-processor machine, or on many <br> machines |
| .NODESET | Aids the calculation of the DC operating point by initializing selected <br> nodes during the first DC operating point calculation |
| .NOISE_CORREL | Specifies correlations between independent noise sources |
| .NWBLOCK | Allows you to control the way Eldo will partition the netlist into several <br> Newton Blocks |
| .OPTION | Allows you to modify Eldo execution behavior by allowing the setting of <br> parameter values other than the default ones |
| .OPTPWL | Allows some precision parameters to be reset during transient simulation <br> for different time windows |
| .OPTWIND | Allows some precision parameters to be reset during transient simulation <br> for different time windows |
| .PARAM | Assigns values to parameter variables used in model and device <br> instantiation statements |
| parameters and Eldo expressions |  |

Table 10-3. Eldo Simulation Control Commands

| Command | Description |
| :--- | :--- |
| .START_TIME | Forces simulation start time |
| .STEP | Performs several simulations while sweeping one circuit parameter or <br> several circuit parameters simultaneously |
| . SUBDUP | Informs Eldo of the duplicate parameters and models which are local to <br> the subcircuit. Also allows access to parameters in the hierarchical form <br> for SimPilot. Useful when Eldo is running in conjunction with SimPilot. |
| .TABLE | Defines tables of run time values to be used in AC, DC or TRANsient <br> analyses |
| .TCL_WAVE | Defines a new waveform using a Tcl function |
| .TEMP | Executes several successive simulations at various temperatures |
| .TSAVE | Saves the state of the simulation at a specified time point |
| .USE | Takes a set of voltages previously saved using the .SAVE <fname> DC <br> command, and inserts these as .NODESET, .GUESS or .IC values at the <br> point of the circuit where this command is present |
| .USE_TCL | Loads a Tcl file to the Eldo Tcl interpreter |

## Circuit Description Commands

Use these commands to describe the attributes of the circuit.
Table 10-4. Eldo Circuit Description Commands

| Command | Description |
| :--- | :--- |
| .A2D | Analog-to-Digital Converter. Establishes the interface <br> connection between Eldo and digital solvers |
| .ADDLIB | Searches a directory for files with file extensions .mod and <br> .ckt (or .sub) and includes in the circuit description (.cir) file <br> the contents of those files whose names correspond to model <br> and subcircuit definitions (respectively) referenced and not <br> defined in the .cir file |
| .AGE_LIB | Defines a set of functions which describe a reliability process <br> for MOS models |
| .AGEMODEL | Allows you to specify the model parameters related to <br> reliability calculations |
| .ALTER | Re-runs Eldo with a modified netlist |
| .BIND | Changes one SPICE description to another equivalent <br> description without editing the description itself |

Table 10-4. Eldo Circuit Description Commands

| Command | Description |
| :---: | :---: |
| .BINDSCOPE | Specifies the hierarchical path to the instance(s) that will be replaced using the .BIND command |
| .CHRENT | Generates a Piece Wise Linear source using straight lines between specified points |
| .CHRSIM | Allows you to use the output of previous simulations as input to the current simulation |
| .CONNECT | Connects two nodes without modifying the circuit description file |
| .D2A | Digital-to-Analog Converter. Establishes the interface connection between digital solvers and Eldo |
| .DEFAULT | Resets the default values for elements, device initial conditions and model parameters |
| .DEFMOD | Maps model names in a netlist to model names specified in .MODEL cards |
| .DEL | Removes a library name from the nominal description |
| .DSPF_INCLUDE | Adds the parasitic elements described inside a specified Detailed Standard Parasitic Format (DSPF) file |
| .END | Marks the end of a simulator input description |
| .ENDL | Marks the end of a library variant description |
| .ENDS | Marks the end of an Eldo subcircuit description. See also .SUBCKT |
| .GLOBAL | Declares global node(s), making them known throughout a circuit without having to declare them in each subcircuit |
| .HDL | Compile and load Verilog-A modules |
| .HIER | Changes the hierarchy separator |
| .IGNORE_DSPF_ON_NODE | Forces Eldo to ignore parasitic elements on a specified node when a DSPF file has been included using the .DSPF_INCLUDE command |
| .INCLUDE | Inserts the contents of a file into a circuit description file |
| .LIB | Inserts model or subcircuit definitions into an input netlist from a library file |
| .LOOP | Inserts a feedback loop between the input and output nodes of an op-amp during transient analysis |
| .MALIAS | Maps model (or subcircuit) names in a netlist to model (or subcircuit) names specified in .MODEL or .SUBCKT cards |

Table 10-4. Eldo Circuit Description Commands

| Command | Description |
| :---: | :---: |
| .MAP_DSPF_NODE_NAME | Maps node references to a new DSPF node name |
| .MODEL | Groups sets of pre-defined parameters which may be used by one or more devices |
| .MODLOGIC | For the definition of digital gate models. <br> NOTE: This is now obsolete syntax and should no longer be used. It has been retained for compatibility reasons only. |
| .MSELECT | Allows you to select models automatically for MOS devices |
| .PART | Instructs Eldo to use the specified algorithm in place of the regular transient algorithm, for a certain selection of instances |
| .PROTECT | Marks the start of a section of a netlist which will not be copied into the output file. Used with .UNPROTECT. |
| .SCALE | Scales device and model parameters of active devices automatically |
| .SELECT_DSPF_ON_NODE | Forces Eldo to select parasitic elements on a specified node when a DSPF file has been included using the .DSPF_INCLUDE command |
| .SETKEY | Defines a key (password), which is associated to a specific model or to all the models of a library |
| .SIGBUS | Sets signals on a bus that has been previously defined via the .SETBUS command |
| .SINUS | Specifies a sine wave |
| .SUBCKT | Marks the start of an Eldo subcircuit definition. See also .ENDS. |
| .TITLE | May be used to define the title of the binary output file |
| .TOPCELL | Selects the TOP cell subcircuit |
| .TVINCLUDE | Allows you to define a bus, specify inputs and check output values using a test vector file |
| .UNPROTECT | Marks the end of a section of a netlist which will not be copied into the output file. Used with .PROTECT. |
| .USEKEY | Provides the encryption key (password) to be used to allow the UDRM API to retrieve an encrypted model parameter's value |
| .USE_VERILOGA | Compile and load Verilog-A modules |
| .VEC | Loads a test vector file |
| .VERILOG | Compile and load Verilog-A modules |

## Command Line Help

## Usage

eldo -help [ commands | devices | sources | manual ]

## Description

Online help accessible from the command line.

## Arguments

Entering the command without any option displays the list of available topics.

- commands

Opens a link document in Acrobat Reader, which will then allow you to select the command you require information on.

- devices

Opens a link document in Acrobat Reader, which will then allow you to select the device model you require information on.

- sources

Opens a link document in Acrobat Reader, which will then allow you to select the source or macromodel you require information on.

- manual

Opens the full Eldo User's Manual, this manual, as a PDF file.

## Command Descriptions

The remaining pages in this chapter describe, in alphabetical order, the Eldo simulator commands.

## .A2D

## Analog-to-Digital Converter

.A2D [SIM=simulator] eldo_node_name

+ [digital_node_name] [MOD=model_name] [parameters_list]
The .A2D and .D2A statements establish the interface connection between Eldo and digital solvers.
i
For Digital-to-Analog, please refer to the ".D2A" on page 577.

Currently, the supported digital solvers are HDL-A and Verilog.

- For Eldo/HDL-A, the converters may be used instead of an equivalent user's defined HDL-A model.
- For Eldo/Verilog, communication is done via the Cadence tool Verimix.


## Note

$\qquad$
For Eldo/Verilog communication done via the Cadence tool Verimix, the A2D and D2A syntax follows the grammar specified in the Cadence manual.


These converters transfer 'analog' Eldo information to some predefined 'digital' types. The following types are implemented: BIt, x01z, STD_LOGIC and REAL.
bit (SLOPE) Two logical values are possible: ' 0 ' and ' 1 '.
$\mathbf{x 0 1}$
X01Z (RC)
STD_VSRC

Three logical values are possible: ' X ', ' 0 ' and ' 1 '.
Four logical values are possible: ' X ', ' 0 ', ' 1 ' and ' $Z$ '.
Same values as type $x 01 z$. Eldo treats this type as the type x 01 z for the A2d, but as the type STD_LOGIC for the D2A.

MVL4

STD_LOGIC (MVL9)

REAL

Same values as type x 01 z . Eldo treats this type as the type x 01 z for the A2D, but as the type BIT (Voltage source) for the D2A.

Nine available logical values: 'U', ' X ', ' 0 ', ' 1 ', ' Z ', ' W ', ' L ' 'H' and '--'. This type corresponds to the VHDL std_logic type defined in the STD_LOGIC_1164 multi-value logic system package in the IEEE library.

Real or float values.

## Global Parameters

The following table shows a global view of the parameters of the .A2d:
Table 10-5. .A2D - Global Parameters

| Name | Description | Default | Units |
| :---: | :---: | :---: | :---: |
| Common for all MODEs |  |  |  |
| CIN | Capacitance of the digital gate input seen by Eldo | 0 | F |
| MODE= BIT \| STD_VSRC |  |  |  |
| VTH | Voltage threshold value for single threshold mode | 2.5 | V |
| VTHREL | Defines the ratio between vioref and vhiref to set vth. The value specified must be between 0.0 and 1.0. Voltage threshold value is calculated using the equation ${ }^{2}$. | 0.5 | - |
| VLOREF | Node voltage used in conjunction with vthrel to set VTH. Voltage threshold value is calculated using the equation ${ }^{2}$. | - | - |
| VHIREF | Node voltage used in conjunction with vthrel to set vth. Voltage threshold value is calculated using the equation ${ }^{2}$. | - | - |
| MODE= X01 \| X01Z | MVL4 | STD_VSRC (FAST_STD_LOGIC) |  |  |  |
| VTH1 ${ }^{1}$ | Lower voltage threshold value for two threshold mode, corresponding to the logical ' 0 ' state | 1.5 | V |
| VTH2 ${ }^{\text {a }}$ | Higher voltage threshold value for two threshold mode, corresponding to the logical ' 1 ' state | 3.5 | V |
| VTH1REL ${ }^{2}$ | Defines the ratio between vloref and vhiref to set vth1. The value specified must be between 0.0 and 1.0. Voltage threshold value is calculated using the equation ${ }^{2}$. | 0.25 | - |
| VTH2REL ${ }^{2}$ | Defines the ratio between vloref and vhiref to set vth2. The value specified must be between 0.0 and 1.0. Voltage threshold value is calculated using the equation | 0.75 | - |
| VLOREF | Node voltage used in conjunction with vth1Rel and vth2rel to set the voltage thresholds. Voltage threshold value is calculated using the equation ${ }^{2}$. | - | - |

Table 10-5. .A2D - Global Parameters

| Name | Description | Default | Units |
| :---: | :---: | :---: | :---: |
| VHIREF | Node voltage used in conjunction with VTH1REL and Vth2Rel to set the voltage thresholds. Voltage threshold value is calculated using the equation ${ }^{2}$. | - | - |
| TX | The ' X ' state will be sent to the DIGITAL part only if the convertor remains in the ' X ' state for more than TX seconds | 0.0 | S |
| RZ | Effective resistance when input is ' $Z$ ' | $\infty$ | $\Omega$ |
| MODE= STD_LOGIC |  |  |  |
| STR | Defines the strength of the logic of the digital node. STRONG strength generates ' X ', ' 0 ', ' 1 ', and wЕak strength generates 'W', 'H', 'L' | STRONG |  |
| VTH | Voltage threshold value for single threshold mode | 2.5 | V |
| VTHREL | Defines the ratio between vloref and vhiref to set vth. The value specified must be between 0.0 and 1.0 . Voltage threshold value is calculated using the equation ${ }^{2}$. | 0.5 | - |
| VTH1 | Lower voltage threshold value for two threshold mode, corresponding to the logical ' $L$ ' state if STR=WEAK, or ' 0 ' if STR=STRONG | 1.5 | V |
| VTH2 | Higher voltage threshold value for two threshold mode, corresponding to the logical ' H ' state if STR=WEAK, or ' 1 ' if STR=STRONG | 3.5 | V |
| VTH1REL | Defines the ratio between Vloref and vhiref to set vth1. The value specified must be between 0.0 and 1.0. Voltage threshold value is calculated using the equation ${ }^{2}$. | 0.25 | - |
| VTH2REL | Defines the ratio between Vloref and vhiref to set Vth2. The value specified must be between 0.0 and 1.0. Voltage threshold value is calculated using the equation ${ }^{2}$. | 0.75 | - |
| VLOREF | Node voltage used in conjunction with vth1ReL and VTH2REL to set the voltage thresholds. Voltage threshold value is calculated using the equation ${ }^{2}$. | - | - |
| VHIREF | Node voltage used in conjunction with VTH1REL and vth2Rel to set the voltage thresholds. Voltage threshold value is calculated using the equation ${ }^{2}$. | - | - |
| TX | The ' $X$ ' state will be sent to the DIGITAL part only if the boundary element remains in the ' X ' state for more than TX seconds | 0.0 | S |
| R | Resistive part of the impedance of the digital gate | $\infty$ | $\Omega$ |
| C | Capacitive part of the impedance of the digital gate | 0.0 | F |

Table 10-5. .A2D - Global Parameters

| Name | Description | Default | Units |
| :--- | :--- | :--- | :--- |
| RZ | Effective resistance when input is ' $Z$ ' | $\infty$ | $\Omega$ |
| MODE $=$ REAL | $5 \times 10^{-3}$ | V |  |
| EPS | Defines the real value threshold |  |  |

1. vth1 has to be specified lower than or equal to $v t h 2$. If not, the simulator will automatically invert vth1 and vth2 values so that vth1 <=vth2.
2. Threshold voltage $=v($ vloref $)+(v($ vhiref $)-v($ vloref $)) \times$ vth $n$ rel, where vth $n$ rel can be vthrel, vth1rel, or vth2rel.

## Parameters

- SIM=simulator

The parameter SIM can take the value of the digital simulator's name: HDLA or VERILOG. The parameter sim is mandatory only for HDL-A.

- eldo_node_name

Name of the node in the analog netlist.

- digital_node_name

Name of the node in the digital description. This parameter is optional. For HDL-A, the syntax is Yxx:position where position is the index of the port.

- MOD=model_name

Name of the model used for the convertor. If model_name is specified, there must be a corresponding .MODEL command:

```
.MODEL model_name A2D|ATOD parameters_list
```

- parameters_list

List of available parameters as described below.

## Note

$\qquad$
For eldo_node_name connected to a PORT of an HDL-A model, parameters_list is ignored. Default values can depend on simulators (HDL-A, Verilog, and so on).

## Parameters for A2D converters (.A2D)

For .A2D the default MODE is $x 01$ for all simulators when two thresholds are specified. If only one threshold is specified, the default MODE is BIt.

## Parameters Common for all Modes

- CIN=value

Capacitance of the digital gate input seen by Eldo (in Farads). Default value is 0.0.

- $\mathbf{T X = v a l u e}$

If $\mathbf{T X}$ is positive, then when the convertor mode is not of type BIT (that is, when the convertor can generate logical ' X ' states) the ' X ' state will be sent to the DIGITAL part only if the convertor remains in the ' $X$ ' state for more than $\mathbf{T x}$ seconds. Default value is 0.0.

## Parameters for MODE=BIT | STD_VSRC (FAST_STD_LOGIC)

- $\mathbf{V T H = v a l u e}$

Voltage threshold value for single threshold mode. The value can be specified using the parameters vloref, vhiref, and vthrel. Default value is 2.5 V .

- Vthrel=value

Defines the ratio between the value of vloref and the value of vhiref to set vth. The value specified must be between 0.0 and 1.0. Default value is 0.5 . If defined the value on $\mathrm{V} \mathbf{V} \boldsymbol{H}$ will be ignored. VTH is calculated using the equation:

```
\(\mathrm{VTH}=\mathrm{V}(\) VLOREF \()+(\mathrm{V}(\) VHIREF \()-\mathrm{V}(\) VLOREF \()) \times\) VTHREL
```

- VHIREF=node_name

Node voltage used in conjunction with vthred to set vth.

- VLOREF=node_name

Node voltage used in conjunction with vthrel to set vth.


## Parameters for MODE=X01 | X01Z | MVL4 | STD_VSRC (FAST_STD_LOGIC)

- VTH1 | VOLTLOW=value

Lower voltage threshold value for two threshold mode, corresponding to the logical ' 0 ' state. The value can be specified using the parameters vloref, vhiref and vthirel. Default value is 1.5 V .

- VTH2 | VOLTHIGH=value

Higher voltage threshold value for two threshold mode, corresponding to the logical ' 1 ' state. The value can be specified using the parameters vloref, vhiref and vth1rel. Default value is 3.5 V .

- VTH1REL=value

Defines the ratio between vloref and vhiref to set vth1. The value specified must be between 0.0 and 1.0. Default value is 0.25 . vтн1 is calculated using the equation:

$$
\text { VTH1 }=\mathrm{V}(\text { VLOREF })+(\mathrm{V}(\text { VHIREF })-\mathrm{V}(\text { VLOREF })) \times \text { VTH1REL }
$$

- vth2rel=value

Defines the ratio between vloref and vhiref to set vth2. The value specified must be between 0.0 and 1.0. Default value is 0.75 . vтн2 is calculated using the equation:

$$
\text { VTH2 }=\mathrm{V}(\text { VLOREF })+(\mathrm{V}(\text { VHIREF })-\mathrm{V}(\text { VLOREF })) \times \text { VTH2REL }
$$

- VHIREF=node_name

Node voltage used in conjunction with vth1rel and vth2rel to set vth1 and vth2.

- VLOREF=node_name

Node voltage used in conjunction with vth1rel and vth2rel to set vth1 and vth2.


## Note

An analog value falling between vth1 and vth2 gives a logical ' X ' state. For MODE=MVL4, there is no analog values that can generate a logical ' $Z$ ' state.

## Parameters for MODE=STD_LOGIC

- STR=WEAK $\mid$ STRONG

Defines the strength of the logic of the digital node. strong strength generates ' X ', ' 0 ', ' 1 ', and weak strength generates 'W', 'H', 'L'. Default is strong.

- VTh=value

Voltage threshold value for single threshold mode. The value can be specified using the parameters vloref, vhiref, and vthrel. Default value is 2.5 V .

- Vthrel=value

Defines the ratio between the value of vloref and the value of vhiref to set vth. The value specified must be between 0.0 and 1.0. Default value is 0.5 . If defined the value on vth will be ignored. vth is calculated using the equation:

$$
\mathrm{VTH}=\mathrm{V}(\mathrm{VLOREF})+(\mathrm{V}(\mathrm{VHIREF})-\mathrm{V}(\mathrm{VLOREF})) \times \text { VTHREL }
$$

- VTH1 | VOLTLOW=value

Lower voltage threshold value for two threshold mode, corresponding to the logical ' L ' state if $\mathbf{S T R}=$ WEAK, or ' 0 ' if $\mathbf{S T R = S T R O N G}$. The value can be specified using the parameters vloref, vhiref and vthirel. Default value is 1.5 V .

- VTH2|VOLTHIGH=value

Higher voltage threshold value for two threshold mode, corresponding to the logical ' H ' state if $\mathbf{S T R}=$ WEAK, or ' 1 ' if $\mathbf{S T R}=\mathbf{S T R O N G}$. The value can be specified using the parameters vloref, vhiref and vthirel. Default value is 3.5 V .

- VTH1REL=value

Defines the ratio between vloref and vhiref to set vthi. The value specified must be between 0.0 and 1.0. Default value is 0.25 . vтн1 is calculated using the equation:

$$
\mathrm{VTH} 1=\mathrm{V}(\text { VLOREF })+(\mathrm{V}(\text { VHIREF })-\mathrm{V}(\text { VLOREF })) \times \text { VTH1REL }
$$

- VTH2REL=value

Defines the ratio between vloref and vhiref to set vth2. The value specified must be between 0.0 and 1.0. Default value is 0.75 . утн2 is calculated using the equation:

```
VTH2 = V(VLOREF ) + (V(VHIREF ) - V(VLOREF ) ) }\times\mathrm{ VTH2REL
```

- VHIREF=node_name

Node voltage used in conjunction with vth1rel and vth2rel to set vth1 and vth2.

- VLOREF=node_name

Node voltage used in conjunction with vth1rel and vth2rel to set vth1 and vth2.

- R=value

Resistive part of the impedance of the digital gate. Default value is infinity.

- C=value

Capacitive part of the impedance (in Farads) of the digital gate. Default value is 0.0 .


## Note

$\square$
An analog value falling between vтн1 and vтн2 generates a logical 'W' state if STR=WEAK, and a logical ' $X$ ' state if STR=STRONG.

## Z state detection on A2D nodes

To enable Eldo to detect an analog 'Z' state on A2D nodes, specify the . Option zdetect command within the netlist. This detection will only be performed on the A2D nodes for which
an Rz value has been specified (either in the A2D card or via the .model A2D command). If the global value for $\mathbf{R z}$ is set using the . OPtion $\mathbf{R z}=$ val command then this will enable Eldo to detect a ' $Z$ ' state on all A2D nodes. A ' $Z$ ' state is detected when the equivalent impedance of the A2D node exceeds the specified $\mathbf{R z}$ value.

## Notes on usage

- Using the . Option zdetect command to detect the 'Z' state will result in extra CPU usage, which is typically an added few percent of the total simulation time.
- The detection of the ' $Z$ ' state is very sensitive to the choice of the time step around the time at which the ' $Z$ ' state should be detected. In some cases there may be a delay between, when the ' $Z$ ' state is detected, and when the ' $Z$ ' state occurs.


## Parameters for MODE=REAL

- $\mathbf{E P S}=\mathrm{value}$

Defines the real value threshold. When the real value coming from the digital simulator differs from the previous value by more than eps, Eldo will take this into account. When the difference is less than EPS, the digital output is considered to be constant.


## Option DEFA2D

It is normally necessary to specify an explicit A2D between ANALOG nodes and HDL-A ports; however, with the following statement specified:
.OPTION DEFA2D=model_name
Eldo will automatically insert an implicit A2D convertor when needed. The following must be defined in the netlist:
.MODEL model_name A2D parameters

Furthermore, it is often necessary to specify mode=bit in the .MODEL model_name command. This is because the default for mode is x01, and very often HDL-A PORTS are of type bit, hence a resulting error mismatch in convertor type would be printed if MODE is not correctly specified. Example:

```
.MODEL model_name A2D mode = BIT
.OPTION DEFA2D = model_name
```

Additionally, these default models must be found in the netlist itself, and cannot be specified via . LIB or .ADDLIB specifications.

## Note

With the option Defand, for any ANALOG node connected directly to an HDL-A IN port, an implicit A2D will be automatically inserted.

## Option D2DMVL9BIT

Enables direct connection between HDL-A ports of type bit with mixed-mode nodes connected to Eldo via convertors of type MVL9 (or std_logic).

The type std_logic is an enumerated type. The type BIT is a subset of std_logic, so a conversion table is required as follows.

Table 10-6. Option D2DMVL9BIT effect

| A2D mode std_logic | HDL-A PORT bit type |
| :--- | :--- |
| $' 0 ', ' L '$ | $' 0 '$ |
| $' 1 ', ' \mathrm{H}^{\prime}$ | $' 1 '$ |
| 'others" | ignored |

## .AC

## AC Analysis

## Parameter-Driven Analysis

```
.AC TYPE nb fstart fstop [SWEEP DATA=dataname] [UIC] [MONTE=val]
.AC TYPE nb fstart fstop [SWEEP parameter_name TYPE nb start stop]
+ [UIC] [MONTE=val]
.AC TYPE nb fstart fstop [SWEEP parameter_name start stop incr]
+ [UIC] [MONTE=val]
```


## Data-Driven Analysis

```
    .AC DATA=dataname [SWEEP DATA=dataname] [UIC] [MONTE=val]
.AC DATA=dataname [SWEEP parameter_name TYPE nb start stop]
+ [UIC] [MONTE=val]
.AC DATA=dataname [SWEEP parameter_name start stop incr] [UIC] [MONTE=val]
```


## List-Driven Analysis

```
.AC LIST {list_of_frequency_points}
```

.AC LIST {list_of_frequency_points}

+ [SWEEP DATA=dataname] [UIC] [MONTE=val]
+ [SWEEP DATA=dataname] [UIC] [MONTE=val]
.AC LIST {list_of_frequency_points}
.AC LIST {list_of_frequency_points}
+ [SWEEP parameter_name TYPE nb start stop] [UIC] [MONTE=val]
+ [SWEEP parameter_name TYPE nb start stop] [UIC] [MONTE=val]
.AC LIST {list_of_frequency_points}
.AC LIST {list_of_frequency_points}
+ [SWEEP parameter_name start stop incr] [UIC] [MONTE=val]

```
+ [SWEEP parameter_name start stop incr] [UIC] [MONTE=val]
```


## Adaptive Analysis

```
.AC ADAPTIVE tolerance_value fstart fstop
```

The .AC command activates the small signal analysis which computes the magnitude and phase of output variables as a function of frequency. The simulator first computes the circuit DC operating point with user specifiable initial conditions; thereafter the behavior of the linearized circuit is computed for a sine input of user specifiable amplitude, phase and frequency range.

Unit amplitude and zero phase gives the circuit transfer function. The inputs are specified via voltage or current sources which have an AC parameter.

The AC results on circuits containing FNS can be altered by the insertion of a .Pz statement in the netlist. The reason being that the .Pz statement implies the writing of FNS equations in such a way that is not as stable as the Eldo native FNS equation. However, this effect can be seen only at very high frequencies.

Whenever a .AC command, a .TRAN command, and a .OP command containing time specifications are in the .cir file, then an AC analysis will be performed at each of these time points. Please see the description of AC in the middle of a .TRAN for further details.

This command can also be used to perform a sweep on a circuit parameter or device.

The amount of information in the .chi file relating to operating point can be limited using the option PRINT_ACOP, see "PRINT_ACOP=0|NO|1|YES" on page 1007.

An adaptive variant of AC analysis can be used when there are ports in the design to generate an accurate touchstone file. Eldo will then adjust the frequency in order that sharp peaks in the AC response are not missed.

Negative frequencies can be specified, but only with the LIN or LIST parameters. For example: .AC DEC $10-1 \mathrm{e} 9$ 1e9 will result in a warning and -1.0 e 9 will be changed into 1.0 with a warning. . AC LIN $100-1 \mathrm{e} 9$ le9 is accepted.

Note
The results of AC analysis runs are output using .PRINT and .PLOT commands.

## Parameters

- type

Can be one of the following:
DEC
Keyword to select logarithmic variation.
ост
Keyword to select octave variation.
LIN
Keyword to select linear variation. Negative frequencies are allowed with this specified.

```
POI
```

Keyword to select a list of frequency points. POI is the same as LIST except that POI expects the number of points (NB) to be specified as it's first argument.

## INCR

Can only be used when the sweep keyword is preceding it. See also the incr specification in "Sweep Parameters" on page 541.

- DATA=dataname

Used in conjunction with the .DATA command. The dataname parameter should be specified using the .DATA command. Please refer to ".DATA" on page 585 for more information.

- LIST

Keyword to select a list of frequency points. Negative frequencies are allowed with this specified.

- nb

Number of points per decade or octave or points over the range from fstart to fstop. This is determined by the preceding keyword.

- fstart

Start frequency in Hertz. This can be specified as a parameter or as an expression.

- fstop

Stop frequency in Hertz. This can be specified as a parameter or as an expression.

- list_of_frequency_points

List of frequency points which can be specified as parameters or as an expression. Values of frequencies must be separated by spaces. When the LISt keyword is specified, the values must be in increasing order, the order can be increasing or decreasing with the por keyword specified.

- UIC

Use initial conditions. If specified, no DC analysis is performed before the AC analysis. Instead the circuit may be initialized using . Restart or . use.

If you have in your input deck both of the following commands: .RESTART file_name, where file_name comes from the results of a TRAN simulation, and if there is a .AC ... uIC command, then the .Restart will be interpreted as:

```
.USE file_name OVERWRITE_INPUT
```

Refer to "Usage of .RESTART and .AC" on page 855 for more information.

- MONTE=val

Monte Carlo analysis. Equivalent to .mc val. The syntax allows a different monte value for each run. However, the actual implementation in Eldo does not account for that: it is the last monte value to be specified in the netlist which will be taken into account.

## - ADAPTIVE

Performs an adaptive AC analysis. Useful if there are ports in the design to have an accurate touchstone file generated. Eldo will adjust the frequency in order that sharp peaks in the AC response are not missed. Otherwise, a large number of points would need to be requested in the AC command in order not to miss such transitions, resulting in very large touchstone files, if any.

- tolerance_value

Specified with an adaptive AC analysis. Tolerance value should be in the range [0.01:0.5]. The smaller the value, the tighter the results. The larger the value, the looser the results.

## Sweep Parameters

This section contains sweep related parameters that are previously unspecified in the Parameters section.

- SWEEP

Specifies that a sweep should be performed on a parameter or device name.

- parameter_name

Name of the parameter or device name to sweep.

- TYPE

As defined previously (DEC, ОСт, ...). When InCR is specified after the sweep keyword, then the functionality is as follows:

## INCR

Increment of the parameter or device name to sweep. When INCR is specified as the TYPE parameter, the value which directly follows (nb) is the incrementing value.

- nb

Number of points per decade or octave or points over the range from start to stop. This is determined by the preceding keyword.

- start

Start value of the sweep.

- stop

Stop value of the sweep.

- incr

Increment of the parameter or device name to sweep.
Note
When INCR is specified as the TYPE parameter, the value which directly follows (nb) is the incrementing value. If INCR is not specified, the incrementing value (incr) must be placed after the start and stop values.

## Examples

$$
\begin{array}{llllllllll}
. a c & \text { dec } & 10 & 1 & 1 g & \text { sweep } & \mathbf{r} 2 & \text { INCR } & 10 & 50 \\
\hline \text { ac dec } & 10 & 1 & 1 g & \text { sweep } & \mathbf{r} 2 & 50 & 500 & 10 &
\end{array}
$$

The two lines above are equivalent. Either can be used to specify a AC analysis from 1 Hz to 1 GHz with 10 analysis points per decade. The sweep specification will force Eldo to carry out an AC analysis on each value of $\mathbf{r} 2$ starting at $50 \Omega$ and stopping at $500 \Omega$ with an incrementing value of $10 \Omega$.

```
vin 2 0 ac 0.5
r1 2 3 5k
c3 3 0 0.1p
.ac dec 10 10e+4 10e+8
.plot ac vdb(3)
```

Specifies an AC analysis from $10 \times 10^{4} \mathrm{~Hz}$ to $10 \times 10^{8} \mathrm{~Hz}$ with 10 analysis points per decade. The $A C$ input parameters are defined using the ac parameter in the voltage source definition. The results of the AC analysis are plotted in dB for the voltage at node 3 of the circuit in the limits specified in the .ac command.

```
v1 1 0 dc 5 ac 0.2
r1 1 2 1k
c1 2 0 1p
.ac oct 8 10e+6 10e+8
.plot ac vdb(2)
```

Specifies an AC analysis from $10 \times 10^{6} \mathrm{~Hz}$ to $10 \times 10^{8} \mathrm{~Hz}$ with 8 analysis points per octave. The input parameters are defined using the ac parameter in the voltage source definition.
The results of the AC analysis are plotted for the voltage in dB at node 2 of the circuit within the limits specified in the .ac command.

1 Examples of this type of analysis can be found in "Tutorials" on page 1341.

Parameters are allowed in AC analysis commands as shown in the following example:

```
.param p1 = 1e9
.ac dec 10 1 p1
```

The following example shows the use of an adaptive AC analysis:

```
* S-par extraction
l1 1 1x 1e-7
r1 1x 2x 10
c1 2x 0 3e-12
T1 2x 0 3x 0 z0=50 Td=1n
c2 3x 0 6e-12
12 3x 4x 2e-7
r2 4x 2 8
T2 2x 0 5x 0 Z0=40 Td=1.5n
Vp 5x 0 0
c11 1 0 10p
c22 2 0 10p
L3 3x 6x 2e-7
R3 6x 5x 2
I1 0 1 iport=1 rport=50
```

```
I2 0 2 iport=2 rport=50
.extract ac yval(sdb (1,1),1.45e8)
.Ffile S sb1.s2p Hz RI
.plot ac sdb (1,1)
.ac adaptive 0.05 1e5 1e11
```

You will see from the simulation results that Eldo computes some pole-zeros otherwise not seen with a standard AC analysis.

## AC in the middle of a .TRAN

Whenever a .AC command, a .TRAN command, and a . OP command containing time specifications are in the .cir file, then an AC analysis will be performed at each of these time points.

In the following example Eldo will perform AC, NOISE and TRAN analyses at time 0, time 5n, and time 7 n :

```
.AC DEC 10 1 1e9
.NOISE v(5) vin 70
.TRAN 1n 20n
.OP 5n 7n
```

1) Please see ".NOISE" on page 744, ".OP" on page 755 and ".TRAN" on page 911 for more details on these commands.

In case there are some .EXTRACT commands related to AC analyses, extract information will be returned for each AC analysis.

When the output is cou format, an extra file, <circuit>_tac.cou is created that holds the results of those AC simulations which are performed from within a transient simulation.

When the output is JWDB, a folder TRAN is created with several AC folders inside, for example AC_1, AC_2.

Limitations:

- AC results performed from within a transient simulation will not be dumped in any of the GWl, PSF, and WSF files.
- If there is a .TEMP or a .STEP command in the input file, the .ext file which normally gets created will not be created in this instance.
- Information related to .extract sweep will not be available.
- Monte Carlo (.mc) enabled if .mC ALl is specified, Worst-Case (.wc), or transientnoise (.NOISETRAN) simulations are disabled.


## .ADDLIB

## Insert a Model or Subcircuit File

```
.ADDLIB N DIR_NAME
```

This command is used to search a directory for files with file extensions .mod and .ckt (or .sub) and include in the circuit description (.cir) file the contents of those files whose names correspond to model and subcircuit definitions (respectively) referenced and not defined in the .cir file. The . ADDLIb command includes a parameter to control the order in which directories are searched.

## Note

When the .ADDLIb command is used with binning models, Eldo searches for all the files <model_name>xxxx.mod inside the directories specified inside . AdDLIb commands.

The following items need to be stressed for upper and lower case character naming rules conventions:

- A filename must be in all upper or all lower case and appended with a lower-case .mod or .ckt or .sub.
.mod for models only
.sub or .ckt for subcircuits only
- Files with upper-case are searched first. For example:

My_2N2222a.mod (not searched)
MY_2N2222A.mod (searched first)
my_2n2222a.mod (searched last)

- For subcircuits: .ckt extension is searched first. .sub is searched last. For example:

```
op11A.ckt (not searched)
OP11A.ckt (searched first)
op11a.ckt (searched second)
OP11A.sub (searched third)
op11a.sub (searched last)
```


## Parameters

- N

An integer between 1 and 6, allocating a priority to the directory search command. When several .ADDLIB commands are included in a circuit description file, then $N$ may be used to determine the order in which the directories are searched. The number 1 allocates the highest priority.

- DIR_NAME

Name of the directory to be searched. The names of the files have to be the same as the subcircuit or model names specified in the netlist.

## Example

```
mn1 a b c d mna w=w l=l
    .addlib 2 /users1/examples/
    .addlib 1 /users1/models/
```

Specifies that all models and subcircuits missing in the input netlist should be searched for and extracted from .mod, .ckt or .sub files contained in the directories </users1/models/> and </users1/examples/> in this order. The file containing the model mna has to be named mna.mod.

## .AGE

## Age Analysis

```
. AGE [TAGE=value] [TUNIT=year \(\mid\) month \(\mid\) day \(\mid\) hour \(\mid\) min \(\mid s e c] ~[N B R U N[S]=\) value]
\(+[\operatorname{LIN}[=\{Y E S|O N| 1\} \mid\{N O|O F F| 0\}] \mid \operatorname{LOG}[=\{Y E S|O N| 1\} \mid\{N O|O F F| 0\}]]\)
+ [LOGMODE_MINEXP=value]
+ [TSTART=value] [TSTOP=value] [TWINDOW=\{(a1,b1) (an,bn)\}]
+ [MODE= sim | load | save | MCload | blockload] [AGELIB=file_name]
\(+[\) AGEALL \([=\{\) YES \(|O N| 1\} \mid\{N O|O F F| 0\}]]\)
+ [RESTRICT_MC=\{YES|ON|1\}|\{NO|OFF|0\}]
+ [ASCII \([=\{\) YES \(|O N| 1\} \mid\{N O|O F F| 0\}]]\)
+ [COMPUTE_LAST \([=\{\mathrm{YES}|\mathrm{ON}| 1\} \mid\{\mathrm{NO}|\mathrm{OFF}| 0\}]]\)
+ [PLOT=\{FRESH_FINAL|ALL\}]
+ [AGEDSIM=\{YES|ON|1\}|\{NO|OFF|0\}]
+ [PRINT_CONFIGURATION=\{YES \(|O N| 1\} \mid\{N O|O F F| 0\}]\)
+ [STRESS_LIST=\{YES \(|\mathrm{ON}| 1\} \mid\{\mathrm{NO}|\mathrm{OFF}| 0\}]\)
+ [STRESS_SORT_NBMAX=value]
+ [STRESS_SORT_REL=value]
+ [STRESS_SORT_ABS=value]
+ [STRESS_LIST_FILE=file_name]
+ [STRESS_LIST_SPLIT_MOS=\{YES \(|\mathrm{ON}| 1\} \mid\{\mathrm{NO}|\mathrm{OFF}| 0\}]\)
+ [STRESS_SORT_ORDER=ASCENDING|DESCENDING]
+ [STRESS_SORT_DELTA=extract_label]
+ [DELTA_VDS=value]
+ [DELTA_VGS=value]
+ [DELTA_VBS=value]
+ [USER_WARNING=\{YES|ON|1\}|\{NO|OFF|0\}]
```

This command activates the Age analysis to test the reliability of a netlist.

For the complete description of Age analysis and information on all reliability commands, see the separate chapter Reliability Simulation.

## .AGE_LIB

## Define Functions For Reliability

.AGE_LIB

+ FILE=library_name
+ FNC_PREFIX=fnc_prefix
+ LEVEL=level1[\{, level2, ..., leveln\}]
+ [SHARED_PATH=yes|no]
+ [PFDIR=library_path]
This command defines a set of functions which describe a reliability process for MOS models.

1 For the complete description of Age analysis and information on all reliability commands, see the separate chapter Reliability Simulation.

## .AGEMODEL

## Reliability Model Parameter Declaration

. AGEMODEL MODEL=model_name [parameter=value]
This reliability analysis command allows the user to specify the model parameters related to reliability calculations.

For the complete description of this command and information on all reliability commands, see the separate chapter Reliability Simulation.

## .ALTER

## Generalized Re-run Facility

```
.ALTER [LABEL]
[ELEMENT]
[SUBCKT]
[COMMAND]
[COMMENT]
.ALTER | .END
```

Used to re-run Eldo with a modified netlist. All Eldo statements between the .ALTER command line and either the next .ALTER or .end command are back-substituted in the original netlist except for certain commands (see below) which are added to the netlist rather than backsubstituted.

The system searches for a match of the component, model, subcircuit or command names in the original netlist and when a match is found the new line is substituted for the original. When no match is found, the new line is simply added, allowing modification of the topology of the circuit.

The following Eldo commands are always added to the netlist with no substitution being attempted.

```
.PRINT, .PLOT, .CONSO, .CONNECT, .EXTRACT, .GLOBAL, . INCLUDE, .OP,
.OPTION, .PARAM, .SENS
```

If a .extract command is present inside a .ALTER command, an EXT folder will be created in the.$w d b$ file on the condition that the .EXTRACT statement remains unchanged for each . Alter file. If this condition is not met, the EXT folder is not created. See ".EXTRACT" on page 637.

In a series of .ALTER commands, all use the initial netlist as the reference to be altered, not the result of the previous .ALTER command.

If one of the .ALTER commands produces an error of non-convergence, Eldo will proceed with the next . Alter command.

The circuit_name.chi ASCII log file contains a trace of all modifications made. The user may annotate the modification trace label string printed in the .chi file using the following syntax:

```
.ALTER <label_string>
```

Use alter_nominai_text to attach a label to the nominal run. The label used is the same as that specified in the command, for example: .ALTER label. This label is printed in the .aex file or attached to the JWDB waveforms.

Use option alter_suffix to switch the naming convention for swept waves used in .alter statements between: $x x x$ and $x x x \_$alter: $X X$.

For JWDB output, the alter index number can be viewed when highlighting waveforms in the EZwave Waves window.

## Note



The .alter command may not be used in conjunction with the .addlib command. In order to use .ALTER with the . Lib command, the key parameter in the . Lib is recommended. An alternative is to use .ALTER with the .LIB command without the KEY parameter provided a . DEL LIB command is added for each library to be replaced.
.del lib can be used in the .alter section. The library name specified in the .del lib command will be removed from the nominal description.
.MPRUN can be used to take advantage of multi-processor machines for the .ALTER command. . ALter has the highest priority when used with .mprun. Please see ".MPRUN" on page 729 for further information.

Error handling of multiple run netlists can be managed with option stoponfirsterror. When set to 2, the first error stops the simulation even if the netlist file contains .ALTER statements for multiple simulation runs. When set to 1, if the netlist file contains . Alter statements, Eldo will stop on the first .alter that has an error, but continue with the remaining .alter statements.

To replace one file by another one when using the Eldo re-run facility, use the option altinc. This forces Eldo to replace the first . Include statement found in an input netlist by the first . include statement found in the .alter section of the netlist.

By default, Eldo substitutes the . Step commands in the main netlist by those found in .ALTER statements. To append . Step commands in .ALTER statements, instead of substituting, use option ALTER_ADDSTEP.
. PARAM statements present in a .ALTER section are systematically added at the end of the netlist being created for the current ALTER run. Eldo will not attempt to replace the parameter name (as was the case in Eldo versions prior to v6.7_1). This can lead to backward compatibility issues if ALTER was used to replace parameters inside . subcкт statements, which is not the usual case. If the parameter is defined at the top, outside of the subcircuit, .PARAM replacement works without any backward compatibility issues, since the last specification prevails; this is the usual case.

## Related Options

"ALTINC" on page 951, "ALTER_ADDSTEP" on page 951, "ALTER_NOMINAL_TEXT" on page 998, "ALTER_SUFFIX" on page 998, "STOPONFIRSTERROR=1|2" on page 960, "WRITE_ALTER_NETLIST" on page 1008.

## Examples

```
alter command example
r1 1 2 1k
r2 2 0 1k
c1 2 0 1n
.ac dec 10 200 1000meg
vin 1 0 ac 1
.plot ac vdb(2) (-90, 0)
.alter
r1 1 2 10k
c1 2 0 100p
.ac dec 15 200 1500meg
.end
```

Specifies two simulation runs. Both perform an AC analysis but certain component values, the number of points and stop frequency of the AC analysis are changed using the .alter command for the second run.
The example below demonstrates the use of the Key parameter in conjunction with the .ALTER command.

```
.lib key=K1 /work/bip/mymod typ
.lib key=K2 /work/mos/mymod typ
...
.alter
.lib key=K2 /work/mos/mymod best
.alter
.lib key=K2 /work/private/mymod typ
.end
```

This command sequence causes three simulations to be performed always with library /work/bip/mymod typ.
In the first simulation, library /work/mos/mymod typ is used.
In the second simulation, library /work/mos/mymod best is used.
In the third simulation, library /work/private/mymod typ is used.

## Note

If there is an error in a .ALTER command, it will be skipped and the next .ALTER command will be used.

The following example shows option ALTER_SUFFix can be used to switch the naming convention for swept waves used in .ALTER statements between: $x x x$ and $x x x$ _alter: $X X$. Run the circuit with and without the option and look at the difference in results.

```
*.option alter_suffix=0
.param VTEST1=1
vdc 1 0 dc VTEST1
vin 2 0 dc 0
v2 4 0 dc 1
etest 3 0 value={mult* (2-v(1,2)*v(1,4))}
```

```
r1 3 0 rval
.dc vin 0 2 0.1
.step param VTEST1 0.5 1.5 0.1
.plot dc i(r1)
.extract label=imax max(i(r1))
.extract label=imin min(i(r1))
.defwave sweep TEST=meas(imax)
.param RVAL=1k
.param MULT=1
.alter first
.param RVAL=1.3k
.param MULT=1.3
.alter second
.param RVAL=0.7k
.param MULT=1.3
.alter
.param RVAL=0.7k
.param MULT=0.7
.alter fourth
.param RVAL=1.3k
.param MULT=0.7
.end
```

The following example shows how to replace one included file by another one when using the Eldo re-run facility, with the option altinc. The new_models file will be included in the re-run simulation instead of models.

```
.include models
.option altinc
r1 1 0 rval
v1 1 0 dc 1
.extract dc i(r1)
.dc
.alter
.include new_models
```

The following examples show the handling of .param statements in .alter sections. The behavior changed in Eldo version v6.7_1.

- Backward compatibility issue if ALTER is used to replace .PARAM inside .subckt statements, which is not the usual case.

```
.subckt foo 1 2
.param p1 = 1
r1 1 2 p1
.ends
i1 1 0 1
x1 1 0 foo
.op
```

```
.alter
.param p1 = 2
. end
```

Here, the netlist corresponding to the first ALTER will now be:

```
.subckt foo 1 2
.param p1 = 1
r1 1 2 p1
.ends
i1 1 0 1
x1 1 0 foo
.op
.param p1 = 2
.end
```

This means that the value of r 1 will remain at 1 . In Eldo versions prior to v6.7_1, p1=1 would have been replaced by $\mathrm{p} 1=2$ even inside the subcircuit.

- No backward compatibility issue

```
.subckt foo 1 2
.param p1 = 1
r1 1 2 p1
.ends
.param p2 = 1
i1 1 0 p2
x1 1 0 foo
.op
.alter
.param p2 = 2
.end
```

Here, for the ALTER run, the value of i1 will be 2, as expected.
-compat flag
Usually in Eldo, .ALTER restarts from the original netlist, however, with the -compat flag set, .alter is cumulative. For example:

```
r1 1 0 1
r2 2 0 1
.alter 1
r1 1 0 2
.alter 2
r2 2 0 2
```

If Eldo is running with the -compat flag set, the second "alter" simulation will be done with both $r 1$ set to 2 (inheritance from later number 1), and r2 set to 2 .

If the -compat flag is omitted, then the second "alter" simulation will be run with r1 set to 1 (original netlist) and $r 2$ set to 2 .

## .BIND

## Configure Spice Descriptions

```
.BIND INST=inst_name [EXCEPT=inst_name]
FROM_SUBCKT=Eldo_subckt_name | FROM_MODEL=HDL_model_name
    TO_SUBCKT=new_Eldo_subckt_name
    [FILE=<file_name> VARIANT=<variant_name>]
| TO_MODEL=new_HDL_model_name
[MAPPING=assoc_file_name | DEFAULT_MAPPING=by_name|by_position]
.BIND INST=inst_name [EXCEPT=inst_name]
    FROM_SUBCKT=Eldo_subckt_name | FROM_MODEL=HDL_model_name
    TO_SUBCKT=new_Eldo_subckt_name
    [FILE=<file_name> VARIANT=<variant_name>]
| TO_MODEL=new_HDL_model_name
    [MAPPING=assoc_file_name | DEFAULT_MAPPING=by_name|by_position]
```

Change one SPICE description (for example, one automatically generated by any schematic tool) to another equivalent description without editing the description itself (or netlisting it again).

The .bIND command is used to substitute any SPICE subcircuit by either another SPICE subcircuit or a behavioral model (VHDL, VHDL-AMS, Verilog or Verilog-AMS).

(1)
For more information on .BIND, see Configuring SPICE Descriptions of the ADVance MS User's Manual.

The . BINDSCOPE command can be used in conjunction with the .BIND command to specify either the full or part of the hierarchical path to the instance(s) that will be replaced.

Note

$\square$
The path specified on the .bIndscope command specifies the hierarchical path for all .BIND commands, therefore the path on the .BIND command must be relevant to the path specified on the .bindscope command.

## Parameters

- INST=inst_name

Specifies the name of the instance(s) that will be replaced with an equivalent SPICE subcircuit or behavioral model. This can be restricted to specific instances of SPICE subcircuits or behavioral models by specifying either FROM_SUBCKT=... or FROM_MODEL=. . . .

- EXCEPT=inst_name

Specifies the name of the instance(s) that will not be replaced with an equivalent SPICE subcircuit or behavioral model.

- FROM_SUBCKT=Eldo_subckt_name

If the Eldo subckt name is not provided, it is equivalent to any subcircuit (in this case, only the instance name is used). If not specified, all the subcircuits will be replaced by the specified subcircuit or HDL model. This can be restricted by specifying INST=inst_name.

- FROM_MODEL=HDL_model_name

If model name is not provided, it is equivalent to any model (in this case, only the instance name is used). If not specified, all the HDL models will be replaced by the specified subcircuit or HDL model. This can be restricted by specifying INST=inst_name.

- TO_SUBCKT=new_Eldo_subckt_name

The Eldo subcircuit name that will replace the existing SPICE or behavioral model(s). The Eldo subcircuit can be replaced with another Eldo subcircuit of the same name from a different library. To do this use the arguments file=file_name and
VARIANT=variant_name.

- FILE=file_name

Name of the file that contains the library.

- VARIANT=variant_name

Name of the variant.

- TO_MODEL=new_HDL_model_name

The behavioral model name that will replace the existing SPICE or behavioral model(s).

- MAPPING=assoc_file_name

Specifies the interface association file to be applied to the port mapping between the model to replace and the new model. This is optional. By default, a mapping by position is used when this file is not provided.

- DEFAULT_MAPPING= by_name|by_position

Defines the port mapping between the model to replace and the new model. The ports can be mapped either by name or by position. This is optional.

For the instance and subcircuit names, SPICE wildcards as listed in Table 10-7 can be used:
Table 10-7. Wildcard Characters

| Character | Description |
| :--- | :--- |
| $*$ | Matches any sequence of characters, including the hierarchy <br> separator "." |
| $?$ | Matches any single character. |
| [abcd] | Matches any character in the specified set. |
| [-abcd] | Matches any character in the specified range, for example [A-Z] <br> matches all alphabetical characters. |

Table 10-7. Wildcard Characters

| Character | Description |
| :--- | :--- |
| [!abcd] | Matches any character not in the specified set, for example [!0-9] <br> matches all characters which are not digits. |

Take care when combining wildcards. If the name used in a .BIND contains square brackets, "[" and "]", these are interpreted as special characters when the wildcard characters "*" or "?" are used. According to UNIX convention, these special characters may be overridden by using the delimiter backslash character " $\$ " which removes the special function of the character that immediately follows it. For example, the following only returns names that end with XVCO1, because, according to UNIX convention, *.XVCO[1] means "all names ending with "XVCO" and followed by the character " 1 "" :

```
.BIND inst=*.XVCO[1] from_subckt...
```

Wildcards may be used either for the instance name or the subcircuit name that will be replaced (inst or from_subckt), but not for the .model card or subcircuit that is used in replacement (to_subckt or to_model). Some examples:

```
adc?top can be adc1top, adcztop but not adc10top.
adc*top can be adc1top, adcztop, adc10top and adc12.b23top.
adc[0-9]top can be adc1top but not adcztop.
```


## Examples

Suppose that we have a SPICE description called top.cir. To substitute all instances of subcircuit inverter that are part of the sub-instance called X1.X2 by the Verilog model inverter compiled in the working library, a new file called new-top.cir can be written as follows:

```
* file new-top.cir
.INCLUDE top.cir
* substitution model declaration
.MODEL new_inverter macro lang=verilogams
+ mod=inverter param: delay=10ns
* substitution command
.BIND inst=x1.x2.*
+ from_subckt=inverter to_model=new_inverter
```

The following example is the same as the previous example however, the .bindscope command is used in conjunction with the .BIND command to define the path to the instances that will be replaced:

```
* file new-top.cir
.INCLUDE top.cir
* substitution model declaration
.MODEL new_inverter macro lang=verilogams
+ mod=inverter param: delay=10ns
* substitution command
.BINDSCOPE PATH=x1.x2
.BIND inst=*
```


## .BINDSCOPE

## Define local scope for .BIND

.BINDSCOPE PATH=scope_path
Specifies the hierarchical path to the instance(s) that will be replaced using the .BIND command. The path specified will apply to all .bind commands in the design. Therefore, the path specified on the .BIND command must be relevant to the path specified on the . BINDSCOPE command.

## Parameters

- PATH=scope_path

Part of or the full hierarchical path to the instance(s) that will be replaced using the .BIND command.

## Note

$\qquad$
4 A warning will be generated if multiple .bindscope commands are defined in a netlist. Only the last occurrence of the command will be used.

## .CALL_TCL

## Call Tcl Function

```
.CALL_TCL [TRAN |AC |DC |...]
+ WHERE=START|START_OF_RUN|END_OF_RUN|END
+ [PLOT=[YES|NO|O|1]] [PLOT_TYPE=[TRAN |AC |DC|...]]
+ [LABEL=alias_name] tcl_function_call
```

This command is used to perform a single call to a Tcl function.
This allows you to dynamically manage User Defined Functions (UDF) written in Tcl language. The functions of the post-processor library and other commands are available through the Tcl interface.


For loading a Tcl file containing functions into Eldo's Tcl interpreter, see the command ".USE_TCL" on page 929. For further information on both commands, see the PostProcessing Library chapter of this manual.

## Parameters

- where

Specify when Eldo must call the tcl function:
START
Only one call at the very beginning of the simulation.

```
START_OF_RUN
```

One call at the beginning of each run.

```
END_OF_RUN
```

One call at the end of each run.

```
END
```

One call at the very end of the simulation.

- PLOT

If the Tcl function returns a wave, this keyword asks Eldo to dump the wave in the output file.

- PLOT_TYPE

Informs Eldo which type of waveform to expect. This is used when the result of the Tcl function is a waveform which must be plotted (PLOT=YES set on the command).

- LABEL

This name will be used to plot the wave in the output file.

- tcl_function_call

The Tcl function. A function can take any kind of arguments: waves, numbers and keywords. These keywords are: IRUN, ICARLO, IALTER which respectively represent the index of the current step, Monte Carlo run, and .alter. nbrun, nbcarlo, nbalter which represent the number of steps, Monte Carlo runs, and .alter.

## Example

```
.call_tcl tran WHERE=END_OF_RUN
+ MY_FUNCTION(v(1),2.0,irun)
```


## .CHECKBUS

## Check Bus Values

```
.CHECKBUS BNAME [VTH[1]=VAL [VTH2=VAL]] [BASE=DEC|OCT|BIN| HEX] [LOCK=1]
+ [REPORTX=0|1] TN VAL {TN VAL}
.CHECKBUS BNAME [VTH[1]=VAL [VTH2=VAL]] [TSAMPLE=VAL] [TDELAY=VAL]
+ [BASE=DEC |OCT|BIN|HEX] [LOCK=1] [REPORTX=0|1] PATTERN BITS {BITS}
```

Checks that the value of the bus has the value VAL at time TN. If an error occurs, the list of the errors are printed inside the .chi file. It is also possible to specify expected values using the pATtERN function.

## Parameters

- BNAME

Bus name.

- TN

Time in seconds at which the bus signal should be equal to VAL volts.

- val

Bus signal voltage level at time TN .

- PATtERN BITS \{BITS\}

Bus signal voltage levels representing the PATtern source. For instance, the $4^{\text {th }}$ VAL specified is the voltage level at time TSAMPLEX4 + TDELAY. Integer values can be specified, a bus value specifying base=bin pattern 101 has the same effect as specifying base=dec pattern 5.

- VTH[1]=VAL

The vth parameters are required by Eldo to compute the HEX (or DEC, OCT, or BIN) value on the bus from the analog value inside Eldo. Then, it compares this value with the value expected and displays the error if they are not the same.

- V th2=VAL

This can be used to plot the indeterminate value as shown below:
When only vтн1 is given:
If value $<\mathrm{VTh}$ then logic state 0 .
If value $>\mathrm{V}$ тн then logic state 1 .
When both vтн1 and vтн 2 are given:
If value < vтн1 then logic state 0 .
If vтн1 < value < vth2 then state X.
If value $>$ vтн2 then logic state 1 .

## - BASE

Keyword indicating that the bus signal number system is to be defined.
OCT

Keyword indicating that bus signals are defined in octal.
DEC
Keyword indicating that bus signals are defined in decimal. Default.

## BIN

Keyword indicating that bus signals are defined in binary.

## HEX

Keyword indicating that bus signals are defined in hexadecimal.

- TSAMPLE=VAL

Time spent at 1 or 0 PATtern value.

- tDELAY=VAL

Delay before the pattern series is started.

- LOCK=1

Forces Eldo to compute specified time points. By default, LOCK is 0 .

- REPORTX=0|1

Print checkbus warnings for undefined X states. By default, reportx is 0. Eldo considers that X states taken by the bus or given in a checkbus list mean that every state is correct for this time point. Thus the check is passed if the bus is X and the check value is 0 or 1 .

## Related Options

max_checkbus, see "MAX_CHECKBUS=ALL|val" on page 1003.

## Examples

```
.CHECKBUS OUT_BUS base=bin vth=2.5
+5000PS 01111
+10000PS 01011
+20000PS 01011
.CHECKBUS OUT_BUS_2 vth=1 vth2=4 base=bin
+ 1000ps 01
+ 7000ps x
+ 12000ps 11
+ 15000ps 01
+ 19500ps 01
```

Refer to ".PLOTBUS" on page 827 for more information.

The following three checkbus lines are equivalent. They use three different bases to specify the expected value on the bus.

```
.checkbus my_bus vth=2.5 base=hex 15m 15 25m 22 45m 91
.checkbus my_bus vth=2.5 base=dec 15m 21 25m 34 45m 145
.checkbus my_bus vth=2.5 base=oct 15m 25 25m 42 45m 221
```

The following example shows how it is possible to specify expected values using the pattern function:

```
.checkbus my_bus vth=2.5 TSAMPLE=10m TDELAY=5m base=hex
+ PATTERN 10 15 22 22 91
```

is equivalent to:

```
.checkbus my_bus vth=2.5 base=hex
+ 5m 10 15m 15 25m 22 35m 22 45m 91
```

1
Refer to the "Pattern Function" on page 332 for more information.

The following example shows how the Lоск parameter can be used:

```
.CHECKBUS S VTH1=0.5 VTH2=4.5 BASE=HEX LOCK=1
+ 15N 0 35N 1 55N 2 75N 3
+ 95N 1 115N 2 135N 3 155N 0
+ 175N 2 195N 3 196.5n 1 215N 0 235N 1
+ 255N 3 275N 0 295N 1 315N 2
```

Eldo will be forced to compute the timepoints $15 \mathrm{n}, 35 \mathrm{n}, 55 \mathrm{n}$, and so on, and the result of the checkbus will produce the following for any accuracy setting:

```
at time 1.965000e+02 ns bus S is 3 and should be 1
```

Without Lоск set, or when Lоск=0, the time reported may vary depending on the circuit and tolerance setting, that is, the nearest point to $1.965000 \mathrm{e}+02 \mathrm{~ns}$ as computed by Eldo. When LOCK $=1$, the time reported will be $1.965000 \mathrm{e}+02 \mathrm{~ns}$ for any accuracy setting.

## .CHECKSOA

## Check Safe Operating Area Limits

```
.CHECKSOA [ANALYSIS] [TSTART=val [TSTOP=val]] [TMIN=val]] [AUTOSTOP]
+ [NOMERGE] [NOLIB] [FILE=filename] [NOXWINDOW]
+ [ENABLE|DISABLE] [SOACODE=range1[{,range_x}]]
+ [INST={list_of_instances }] [SUBCKT={list_of_subckts }] [RUNTMSG]
```

Causes Eldo to check for any violations of the circuit safe operating area (SOA) limits specified via the . SETSOA command.

## i See ".SETSOA" on page 872 for more details.

If an entity has more than one set of the same specifications, but with different boundaries, Eldo merges the specifications by taking the more restrictive constraint. This is the default mode.

You can filter SOA checks to enable/disable based on a code assigned to any SOA check using the SOACODE parameter of the . SEtSOA command.

The targets of the SOA can also be specified with more accuracy to enable/disable the SOA checks on specific instances or parts of the circuit hierarchy.

## Parameters

- ANALYSIS

Optional. By default, it depends on the analysis specified in the netlist. Can be one of the following:

AC
Specifies that the checks are required for an AC analysis.
DC
Specifies that the checks are required for a DC analysis.

## TRAN

Specifies that the checks are required for a transient analysis.
DCSWEEP
Specifies that the checks are required for a DCSWEEP analysis.
FOUR
Specifies that the checks are required for an FFT analysis.

## TMODSST|TSST|FSST

Specifies that the checks are required for an RF analysis.

- TSTART=val

Specifies start time value when SOA should be checked. Default is the first time point of the TRAN simulation.

- TSTOP=val

Specifies stop time value when SOA should be checked. Default is the last time point of the TRAN simulation.

- TMIN=val

Specifies the value for a minimum time window when SOA should be checked. When this value is set, Eldo will ignore transient SOA violations lasting less than tmin seconds.
Default value is 0 .

- autostop

Forces Eldo to quit immediately if an SOA specification is violated.

- nomerge

By default, if an entity has more than one set of the same specifications, but with different boundaries, Eldo merges the specifications by taking the more restrictive constraint. Use nomerge to take the constraints into account as specified in the netlist. For example:

```
.setsoa label=m1 d m5 vgs=(*,1.36)
.setsoa label=m2 d m5 vgs=(*,1.37)
```

The second constraint will be ignored, since the constraint labelled m1 implies constraint m2. If the keyword nomerge is specified on the .checksoa command, the two constraints will be taken into account as specified in the netlist.

- nolib

Eldo will not consider SOA cards which are imported from . LIb. Instead, it will only consider those specified in the .cir file or from . include files.

- $\mathbf{F I L E}=$ filename

Specifies a file to which SOA results will be written instead of the standard ASCII output file. If no violations occur the message "No SOA violation detected" will be printed in the file.

- noxwindow

Forces Eldo not to write the X-axis window information if the SOA is violated.

- ENABLE|DISABLE

Enable or disable the indicated targets. By default, they are enabled.

- SOACODE=range

A single code or range of codes assigned to SOA checks in . SETSOA commands. Based on these codes you can filter SOA checks to enable/disable. The codes should be positive integer quantities. Separate a list of codes by commas. A range of contiguous codes can also be specified using an $\mathrm{n} 1: \mathrm{n} 2$ syntax to designate all codes between n 1 and n 2 . The soacode,
if specified, must be placed immediately following the enable|disable parameter. For example:

```
.CHECKSOA TRAN ENABLE SOACODE=1,2 INST=x1*
```

- INST

Restricts (enable/disable) the scope of . SETSOA cards to the instances specified by list_of_instances. Only . SETSOA commands which explicitly reference the instance will be (enabled/disabled) .

- SUBCKT

Restricts (enable/disable) the scope of . SETSOA cards to the subcircuit instances specified by list_of_subckts. Only . SETSOA commands which are in the subcircuit definition or which explicitly reference the instance will be enabled/disabled.

- RUNTMSG

Forces Eldo to display the SOA violations on screen as they are detected during the simulation. This means you do not have to wait till the end of the simulation to see when the violations occur. The violation information displayed on screen is represented differently to what is printed in the .chi file. If the XAXIS parameter is specified in the .SETSOA command then violations which occur within this time span and continue afterwards will only be displayed on screen when the XAXIS time span finishes. Violations which start and finish within the XAXIS time span will not be displayed.

## Example

```
* Restrict SOA to list subckt instances
.model resis res r= 1k dev/gauss=10%
.subckt xsub a b
r1 a b resis 1k
.setsoa E I(R1)=(1.80u,1.90u) !<= This card will be active
* for X1 only
.ends xsub
v1 1 0 pwl(0 0 10n 10)
x1 1 2 xsub
x2 1 2 xsub
r2 2 0 1k
.setsoa D X1.R1 i=(1.80u,1.90u) !<= This soa is active
.setsoa D X2.R1 i=(1.80u,1.90u) !<= This one is not active
.checksoa subckt=x1
.tran 1n 10n
.extract tran I(X1.R1)
.end
```

In the example above, two cards will be kept: the one in xsub corresponding to x 1 ; and the top level card .setsoa D X1.R1.

## .CHRENT

## Piece Wise Linear Source

```
.CHRENT NODE TN VN {TN VN} [P|F]
.CHRENT NODE (TN VN {TN VN}) FACTN {(TN VN {TN VN}) FACTN} [P|F]
```

Generates a Piece Wise Linear source using straight lines between specified points as described below.

## Parameters

- NODE

The source is placed between node nODE and ground.

- VN

Value of the source at time $\boldsymbol{T i}$ in volts. The source value at intermediate times is provided by linear interpolation.

- TN

Time in seconds, at which $\boldsymbol{V i}$ is supplied, where $T i<T i+1$.

- FACTN

Factor that indicates how many times the previous block is repeated.

- $\mathbf{P}$

Defines a periodic signal type. Default signal. Optional.

- $F$

Defines a non-periodic signal type. Optional.

## Notes

The time declared using the first syntax above is an absolute time whereas that declared using the second syntax in the parentheses is relative. This makes life easier when dealing with complex waveforms since calculation of absolute times can be very tedious.

For non-periodic curves, the voltage applied to node node between time 0 and time $\mathrm{T1}$ is equal to V 1 , with the voltage applied at time TN being vn. Time TN specifies the last time interval.

For periodic curves, the voltage applied to node node between time 0 and T 1 is V 1 . The period however, is specified as TN minus $\mathrm{T1}$ enabling an initialization phase before starting a periodic signal.

A piece-wise linear signal may be declared both by a . chrent command and a Piece Wise Linear signal on an independent source $v \times x$. The repetition factor, however, may only be declared using the .Chrent command.

## Examples

```
.chrent n3 0n 5.0 10n 5.0 12n 0 36n 0 40n 5.0 p
```

Specifies a periodic signal applied between node n3 and ground. It starts at 0 s with 5 V , stays there for 5 ns , falls in 1 ns to 0 V , stays there for 32 ns , then it rises in 2 ns to 5 V . This signal repeats with a period of 40 ns .

Figure 10-1. Piece Wise Linear Example 1


This example illustrates a way of describing a function which is periodic for a given period of time, then becomes periodic with a different waveform for another period of time, and so on. The values not in parentheses indicate how often the block is repeated.

Figure 10-2. Piece Wise Linear Example 2


## .CHRSIM

## Input from a Prior Simulation

```
.CHRSIM IN OUT FILE [TSTART=V1] [TSTEP=V2] [BP=0|1|2]
+ [ZOOMTIME] [FORMAT=WDB] [RUN=VAL] [TYPE=CURRENT|VOLTAGE]
```

The .chrsim command enables the user to use the output of previous simulations as input to the current simulation. The previous simulation data must have been generated by a DC sweep or a transient analysis. The simulator assigns the output obtained at node out of the circuit FILE to the node IN of the current simulation.
. Chrsim can read in any waveform from a waveform file using the EZwave name. It can handle any waveform sent to any waveform file: currents, Monte Carlo runs, and so on. For example, maximum and minimum waveforms created by a .MC analysis (without the aLL keyword specified) are recognized by .CHRSIm for example:

```
.chrsim x "v(2)_H" e.wdb bp=2
```

This would read in the waveform $\mathrm{v}(2) \_\mathrm{H}$ from the output file $e . w d b$, and use it as an input at node x in the current simulation. The waveform $\mathrm{v}(2) \_\mathrm{H}$ is a maximum result coming from a Monte Carlo run.

## Note



There is a difference in the . Chrsim syntax between Eldo and ADMS. In ADMS, the name of the top design must be declared for previously simulated waveforms. For example:
.CHRSIM O1 V(O1) ./inv1 BP=2 TYPE=voltage ! for Eldo
.CHRSIM $01 \mathrm{~V}(:$ inv1:01) ./inv1 BP=2 TYPE=voltage ! for ADMS

## Parameters

- IN

Name of the input node of the current simulation.

- out

Name of the node, or waveform, previously simulated in FILE.

- FILE

Name of the circuit previously simulated to be read. This file must be located in the same directory as the file to be simulated, and node out must have been requested via a .PLOT command. If you specify the full name of the file, including extension, the fOrmat specification will not be required. By default, if no extension is provided, Eldo will look for a.cou file unless format is specified.

- TSTART=V1

Starting position in the FILE.wdb file in seconds.

- TSTEP=V2

Selects one point every tster points in the FILE.wdb file.

- $\quad \mathrm{BP}=0$

Input wave will not impose time points on Eldo. Default.

- $\quad \mathbf{B P}=2$

Eldo will make a time point at each time point found in the input wave.

- $\quad \mathbf{B P}=1$

Intermediate between cases 0 and 2. Eldo will impose a time point if the variation of the input wave is significant enough.

- zOOMTIME

Reuse the results of a simulation with .Chrsim by modifying the time scale. If the simulation read back corresponds to a TRAN simulation, and if the current simulation is also a transient simulation for which the simulation duration is known (that is, .TRAN command present in the netlist), then the simulation time as read in the file will be multiplied by TSTOP/TSTOP_READ.
TSTOP is the simulation duration as specified in the .TRAN command. TSTOP_READ is the simulation duration as read in the 'cou-format' file specified in the . Chrsim command.

- FORMAT=WDB
.chrsim will retrieve data values from a JWDB file with extension . $w d b$. Not required if you specify the extension in FILE.
- $\quad$ RUN=VAL

Specifies which simulation run the results will be used from, for use with multi-run analysis. Default is 1 (first simulation run).

- TYPE=CURRENT | VOLTAGE

Specifies whether to create a current or voltage source. Default is voltage.

## Examples

.chrsim n7 a8 adder.wdb
Specifies the output of the circuit adder at node a8 to be applied at node $n 7$ of the current simulation. Eldo reads the file $a d d e r . w d b$ which must be in the same directory.

```
.chrsim i7 o2 mult.wdb tstart=4n tstep=1n
```

Specifies the output of the circuit mult at node o2 to be applied at node i7 of the current simulation. The signal is applied 4 ns in from its starting point at 1 ns intervals of the waveform. Eldo reads the file mult.wdb which must be in the same directory.

## .COMCHAR

## Change Comment Character

. СОMCHAR char $\{$ char\}
This command is used to change the comment character on an input file. Several comment characters can be specified as active at the same time in a single . ComChar command. Any new . Сомсhar command will append the new character to the list of comment characters.

## Parameters

- char

A list of comment characters can be specified. The command accepts any character. Usually, only the $\$$ or the ! characters are used. Unexpected behavior can be obtained when specifying other characters. The default is character '!'. By default, Eldo also allows the '*' character as an inline comment except on .Extract, .DEFMAC, .DEFWAVE, .meas,
. OBJECTIVE, and . PARAM commands.

## Notes

- The first call to . Сомсhar overwrites the default comment character, that is, character '!' in Eldo default mode.
- Specifying option cumul_comchar= 0 returns to the exclusive mode (pre-v6.4 default scheme) where only the last . сомснar specified is effective. An alternative is to specify command .RESETCOMCHAR <list_of_char> which will overwrite the list of comment characters.
- The following warning will be printed when the comment character is $\$$ :

```
Warning 1605: Eldo uses the $ character as a comment character.
There are several ways to use this inside the netlist:
+ - to specify string parameters ($(FOO))
+ - to specify environment variables (.include $MY_PATH/foo.inc)
+ - to call macros defined by a .defmac (.param foo = $sum(2,3))
+ If Eldo returns a parsing error on a line containing such an
+ element, try enclosing it between ' or ", for example:
'$(FOO)' / .include "$MY_PATH/foo.inc" / .param foo = '$sum(2,3)'
```

Enclose the $\$$ (param_name) between single quotes ' in order to use it when the $\$$ is used as a comment character.

## Examples

To tell Eldo that the comment character on an input file is ' $\$$ ' rather than the default '!', use the command:

```
.comchar $
```

The example below shows how a list of comment characters can be made active in a single command, and then how the list is appended to with a further command:

```
Title
.COMCHAR $#!
.COMCHAR /
i1 1 0 1 !default comment
r1 1 0 3 $another comment
r2 1 0 3 #another comment
r3 1 0 3 /another comment
.dc
.end
```


## .CONNECT

## Connect Two Nodes

.CONNECT N1 N2
The . Connect command is used to connect the nodes N 1 and N 2 without modifying the circuit description file. Wildcard characters ' $*$ ' can be specified to make multiple connections with a single command, Eldo will attempt to connect any node name which matches the pattern.

## Parameters

- $\mathrm{N} 1, \mathrm{~N} 2$

Names of the nodes to be connected.

## Examples

```
.connect n7 n5
```

Specifies the connection of the nodes $n 7$ and $n 5$.

```
.connect in<*> 1
v1 1 0 1
r1 in<1> 0 1
r2 in<2> 0 1
r3 in<3> 0 1
.op
.end
```

This example shows wildcards being used to make multiple connections. Eldo will connect nodes in<1>, in<2>, and in<3> to node 1.

## .CONSO

## Current Used by a Circuit

.CONSO VN \{VN\}
The .conso command computes and displays the average current flowing through the specified voltage source(s) during the simulation period. There is no limit to the number of .conso commands that may be present in an input netlist.

## Parameters

- vN

Name of the voltage source(s).

## Note

This command may only be used in conjunction with a transient analysis.

## Examples

```
vdd 100 101 5v
.conso vdd
.tran 1ns 100ns
```

Specifies a printed output of the average current flowing through the voltage source vdd over the length of the circuit simulation.

```
v1 n1 0 5
v2 n3 n4 2
..
.conso v1 v2
.tran 1ms 50ms
```

Specifies a printed output of the average current flowing through the voltage sources v1 and v 2 over the length of the circuit simulation.

## .CORREL

## Correlation between Parameters

```
.CORREL [PARAM=]param_list cC=VAL
.CORREL DEV[ICE]=device_list PARAM=param_list cc=VAL
```

Correlations can be specified between parameters during a Monte Carlo analysis. This is done by specifying the relations between the different parameters. Correlation coefficients can be given for groups of two parameters. It can also be given for a list of parameters, in such a case the correlation coefficient will be the same for each couple. For example, in the list a, b, c the couples will be (a, b), (b, c) and (c, a).

It is also possible to specify correlations for each subcircuit instance via parameters which are assigned devx variation.

## (1) For more information see DEVX in .PARAM.

From the correlated parameters specified via .correl statements, Eldo retrieves a set of uncorrelated parameters and computes a conversion matrix between the uncorrelated parameters and the correlated parameters. This is done using the PCA method (Principal Component Analysis). Then, it is on these uncorrelated parameters that the MC variations will be performed. Eldo will then compute the new values for the correlated parameters, using the transformation matrix.

## Parameters

- PARAM=param_list

List of parameters to be correlated. There is no limit to the number of parameters that can be listed. They can be listed in a number of ways, as follows:

```
.correl a b c cc=val
.correl param=a b c cc=val
.correl param=a, b, c cc=val
.correl param={a b c} cc=val
.correl param={a, b, c} cc=val
```

When used with Device it represents a list of parameters which have devx specifications.

- $\mathbf{c c =}=\mathrm{VAL}$

Correlation coefficient. This can be any real number between -1 and +1 .

- DEVICE=device_list

List of devices and subckt instances.

## Examples

The following command:

```
.CORREL param=p1,p2,p3 cc=0.1
```

is equivalent to the following three .Correl commands:

```
.CORREL p1 p2 cc=0.1
.CORREL p1 p3 cc=0.1
.CORREL p2 p3 cc=0.1
```

The following example shows how parameters with цот variations can be correlated:

```
.param pc=10p LOT=10%
.param rc=1k LOT=5%
.SUBCKT cmod a b
C1 a b pc
R1 a b rc
.ENDS
X1 4 0 cmod
x2 6 8 cmod
.CORREL param=pc,rc cc=0.9
```

Eldo will generate pseudo-random values for pc and rc using 0.9 as their coefficient of correlation.

The following example shows how parameters with devx variations can be correlated:

```
.param pc=10p DEVX=10%
.param rC=1k DEVX=5%
.SUBCKT cmod a b
C1 a b pc
R1 a b rc
.ENDS
x1 4 0 cmod
x2 6 8 cmod
.CORREL device=x1,x2 param=pc,rc cc=0.1
```

The .correl command will create a relation between $\mathrm{x} 1 . \mathrm{pc}$ and $\mathrm{x} 2 . \mathrm{pc}$ and also between $\mathrm{x} 1 . \mathrm{rc}$ and $\mathrm{x} 2 . \mathrm{rc}$ with a coefficient of 0.9.

Note
In the case of correlation on devices, and when the parameter list is not specified, then all parameters with Devx variations which are used in the X instances given in the device list will use the same correlation coefficient cc.

## .D2A

## Digital-to-Analog Converter

.D2A [SIM=simulator] eldo_node_name

+ [digital_node_name] [MOD=model_name] [parameters_list]
The .D2A statement establishes the interface connection between digital solvers and Eldo.

For Analog-to-Digital, please refer to ".A2D" on page 528.

When the digital value driving the "mixed-signal" is logic ' 1 ', the voltage on the analog side of the signal is driven to the voltage value defined by the parameter vhi. When the logic level is ' 0 ', the analog voltage is driven to that defined by VLO. TRISE and TFALL are used to specify the duration of the linear rise and fall slopes between the voltages VHI and VLo. Values of "zero" for TRISE and TFALL are not allowed since this would represent an infinite energy transition.

The following table shows a global view of the parameters of the .D2A:
Table 10-8. .D2A Global Parameters

| Name | Description | Default | Units |
| :---: | :---: | :---: | :---: |
| MODE= BIT \| X01 | MVL4 | STD_VSRC |  |  |  |
| VHI | Higher voltage value, corresponding to the logical ' 1 ' state. If VHIREF is specified the parameter VHI will be ignored. | 5 | V |
| VLO | Lower voltage value, corresponding to the logical ' 0 ' state. If VLOREF is specified the parameter VLO will be ignored. | 0 | V |
| VHIREF | Value of this node is used to set the higher voltage reference, corresponding to the logical state ' 1 '. If specified the value of vHI will be ignored. | - | - |
| VLOREF | Value of this node is used to set the lower voltage reference, corresponding to the logical state ' 0 '. If specified the value of VLO will be ignored. | - | - |
| TRISE | Defines the rise time for the voltage source, going from VLO to VHI value | 2ns | S |
| TFALL | Defines the fall time for the voltage source going from vHi to vio value | 2ns | S |
| MODE $=$ X01Z \| STD_LOGIC |  |  |  |
| VHI | Higher voltage value, corresponding to the logical ' 1 ' state that will be reached if the convertor is applied on a node with infinite input resistance | 5 | V |

Table 10-8. .D2A Global Parameters

| Name | Description | Default | Units |
| :---: | :---: | :---: | :---: |
| VLO | Lower voltage value, corresponding to the logical ' 0 ' state that will be reached if the convertor is applied on a node with infinite input resistance | 0 | V |
| VHIREF | Value of this node is used to set the higher voltage reference value. This corresponds to the logical state ' 1 'that will be reached if the boundary element is applied on a node with infinite input resistance. | - | - |
| VLOREF | Value of this node is used to set the lower voltage reference value. This corresponds to the logical state ' 0 ' that will be reached if the boundary element is applied on a node with infinite input resistance. | - | - |
| TRISE | Rise time for the current source. Commutation time ' 0 ' $\Rightarrow$ ' 1 ' value | 2ns | S |
| TFALL | Fall time for the current source. Commutation time ' 1 ' $\Rightarrow$ '0' value | 2ns | S |
| RZ | Effective resistance when input is ' $Z$ '. | $\infty$ | $\Omega$ |
| RRISE | Impedance for a strong logical ' 1 ' state. The conductance is then $G=1 /$ RRISE and the current $I=V H I / R R I S E$ | 1 | $\Omega$ |
| RFALL | Impedance for a strong logical ' 0 ' state. The conductance is then $G=1 /$ RFALL and the current $I=V L O / R F A L L$ | 1 | $\Omega$ |
| LOWCAP | Capacitance for a logical ' 0 ' state ('L'). This capacitance models the output capacitance of the digital gate | 0 | F |
| HIGHCAP | Capacitance for a logical ' 1 ' state ('H'). This capacitance models the output capacitance of the digital gate | 0 | F |
| ZCAP | Capacitance for a logical ' $Z$ ' state. This capacitance models the output capacitance of the digital gate | 0 | F |
| XEVAL= PREVIOUS | Forces the corresponding ' X ' state analog value to the previous analog value before the state changed to ' X ' | - | - |
| MODE= STD_LOGIC |  |  |  |
| WEAHIGHRES | Impedance for a weak (or resistive) logical ' 1 ' state ('H'). The conductance is then $G=1 /$ WEAHIGHRES and the current I=VHI/WEAHIGHRES | 1 | $\Omega$ |
| WEALOWRES | Impedance for the weak (or resistive) logical ' 0 ' state ('L'). The conductance is then $\mathrm{G}=1$ /WEALOWRES and the current is I=VLO/WEALOWRES | 1 | $\Omega$ |

Table 10-8. .D2A Global Parameters

| Name | Description | Default | Units |
| :--- | :--- | :--- | :--- |
| MODE $=$ REAL | INTEGER | s |  |
| TRISE | Defines the rise time. Commutation time ' 0 ' $\Rightarrow$ ' 1 ' value. <br> Ignored if TCOM is specified | 2 ns | s |
| TFALL | Defines the fall time. Commutation time ' 1 ' $\Rightarrow$ ' 0 ' value. <br> Ignored if TCOM is specified | 2 ns | s |
| TCOM | Defines the commutation time. Eldo switches from the <br> previous value to the new value with a slope of time TCom. <br> If specified then TRISE or TFALL parameters are ignored | 2 ns | s |

## Parameters

- SIM=simulator

The parameter sim can take the value of the digital simulator's name: hdla or verilog. The parameter SIm is mandatory only for HDL-A.

- eldo_node_name

Name of the node in the analog netlist.

- digital_node_name

Name of the node in the digital description. This parameter is optional. For HDL-A, the syntax is Yxx :position where position is the index of the port.

- MOD=model_name

Name of the model used for the convertor. If model_name is specified, there must be a corresponding .MODEL command:

```
.MODEL model_name D2A|DTOA parameters_list
```

- parameters_list

List of available parameters as described below.
Note
For eldo_node_name connected to a PORT of an HDL-A model, parameters_list is ignored. Default values can depend on simulators (HDL-A, Verilog, and so on).

## Parameters for D2A converters (.D2A)

For .D2A the default mODE is X01 for all simulators.

## Parameters for MODE=BIT |X01| MVL4 | STD_VSRC

These modes emulate a voltage source for Eldo. Additional parameters:

- VHI |VOLTHIGH=value

Higher voltage value, corresponding to the logical ' 1 ' state. Default is 5 V .

- VLO|VOLTLOW=value

Lower voltage value, corresponding to the logical ' 0 ' state. Default is 0 V .

- VHIREF=node

Value of this node is used to set the higher voltage reference, corresponding to the logical ' 1 ' state. If specified the value of $\mathrm{vhi} \mid$ Volthigh will be ignored.

- VLOREF=node

Value of this node is used to set the lower voltage reference, corresponding to the logical ' 0 ' state. If specified the value of vlo|voltlow will be ignored.

- TRISE $\mid$ TIMERISE=value

Defines the rise time for the voltage source, going from VLO to VHI value. Unit is seconds. Default value is 2 ns .

- TFALL | TIMEFALL=value

Defines the fall time for the voltage source going from VHI to VLO value. Unit is seconds. Default value is 2 ns .

## Note

For MODE $=\mathrm{XO} 0$, the logical ' X ' state is ignored, that is, the analog value remains the same. For mODE=MVL4, the logical ' X ' and ' $Z$ ' states are ignored, that is, the analog value remains the same.

## Parameters for MODE=X01Z | STD_LOGIC

When the mode of the converter is x01Z|STD_LOGIC|MVL9 these modes emulate an IRC (or IGC) convertor in Eldo. The convertor consists of a current source in parallel with a conductance in parallel with a capacitor with everything connected between the current node and the ground node. Several IRC convertors can be placed on one node and depending on the strength of the signals applied on each of them, the conflicts can be resolved with one of the modes. The values of this IGC vary depending on the state of the D2A convertor, these different values are computed according to the values specified in the D2A statement. If no values are specified, then the default values are used.

Additional parameters for these modes:

- VHI|VOLTHIGH=value

Higher voltage value, corresponding to the logical ' 1 ' state that will be reached if the convertor is applied on a node with infinite input resistance. Default value: 5 V .

- vlo|voltlow=value

Lower voltage value, corresponding to the logical ' 0 ' state that will be reached if the convertor is applied on a node with infinite input resistance. Default value: 0 V .

- VHIREF=node

Value of this node is used to set the higher voltage reference, corresponding to the logical ' 1 ' state. If specified the value of $\mathbf{v h i} \mid$ Volthigh will be ignored.

- VLoref=node

Value of this node is used to set the lower voltage reference, corresponding to the logical ' 0 ' state. If specified the value of vlo|voltlow will be ignored.

- TRISE $\mid$ TIMERISE=value

Rise time for the current source. Commutation time ' 0 ' $\Rightarrow$ ' 1 ' value. Unit is seconds. Default value: 2 ns .

- TFALL |TIMEFALL=value

Fall time for the current source. Commutation time ' 1 ' $\Rightarrow{ }^{\prime} 0$ ' value. Unit is seconds. Default value: 2 ns .

- RZ $\mid$ HIGHIMPRES=value

High impedance to model a high impedance state ('Z'). In this case, the conductance ( $\mathrm{G}=1 / \mathrm{Rz}$ ) will be small, and the current $\mathrm{I}=0$. Default is $1 \Omega$.

- RRISE|STRHIGHRES=value

Impedance for a strong logical ' 1 ' state. The conductance is then $G=1 /$ RRISE and the current I=vhi /RRISE. This resistance is usually small. Default is $1 \Omega$.

- RFALL | STRLOWRES=value

Impedance for a strong logical ' 0 ' state. The conductance is then G=1/RFALL and the current $\mathrm{I}=\mathrm{VLO} / \mathrm{Rfall}$. This resistance is usually small. Default is $1 \Omega$.

- LOWCAP=value

Capacitance for a logical ' 0 ' state ('L'). This capacitance models the output capacitance of the digital gate. Default is 0 F .

- HIGHCAP=value

Capacitance for a logical ' 1 ' state (' $H$ '). This capacitance models the output capacitance of the digital gate. Default is 0 F .

- ZCAP=value

Capacitance for a logical ' $Z$ ' state. This capacitance models the output capacitance of the digital gate. Default is 0 F .

- XEVAL=PREVIOUS

When this is specified, the corresponding ' X ' state analog value will be the previous analog value before the state changed to ' X ', that is, if the digital state changed from ' $L$ ' $=>$ ' X ' then the analog value will stay at vzo. The default value is computed from the impedances set in .D2A or .model statements for the ' $X$ ' states.

## .D2A

## Parameters for MODE=STD_LOGIC

- WeAhIGHRES=value

Impedance for a weak (or resistive) logical ' 1 ' state (' $H$ '). The conductance is then $\mathrm{G}=1 /$ /weAhighres and the current $\mathrm{I}=\mathrm{vhi} / \mathrm{WeAhighres}$. This resistance is of course larger than RFALL and RRISE. Default is $1 \Omega$.

- WEALOWRES=value

Impedance for the weak (or resistive) logical ' 0 ' state ('L'). The conductance is then $\mathrm{G}=1 /$ wealowres and the current is $\mathrm{I}=\mathrm{Vhi} /$ WeAlowres. This resistance must be larger than RFALL and RRISE. Default is $1 \Omega$.

## Logical states

## ' $X$ ' State

For the logical ' X ' state which is also referred to as 'strong X ', the corresponding conductance (GX), capacitance (CX), transition time (TX) and current source (IX) values are calculated as shown below:

$$
\begin{aligned}
& G X=\frac{R^{2} I S E^{-1}+R F A L L^{-1}}{2} \\
& C X=\frac{L O W C A P+H I G H C A P}{2} \\
& T X=\frac{T R I S E+T F A L L}{2} \\
& I X=\frac{(V H I+V L O)}{2} \times G X
\end{aligned}
$$

## 'W' State

For the logical 'W' state which is also referred to as 'strong W' the corresponding conductance (GX), capacitance (CX), transition time (TX) and current source (IX) values are calculated as shown below:

$$
\begin{aligned}
& G X=\frac{W_{E A H I G H R E S}{ }^{-1}+\text { WEALOWRES }^{-1}}{2} \\
& C X=\frac{\text { LOWCAP }+H I G H C A P}{2} \\
& T X=\frac{T R I S E+\text { TFALL }}{2} \\
& I X=\frac{(V H I+V L O)}{2} \times G X
\end{aligned}
$$

## Note

The capacitance (cx) and transition time (TX) are the same for both ' X ' and ' W ' states.

## Parameters for MODE=REAL|INTEGER

Eldo will read from a DIGITAL simulator the real value instead of a logical value. Additional parameters:

- TRISE|TIMERISE=value

Defines the rise time. Commutation time ' 0 ' $\Rightarrow$ ' 1 ' value. Unit is seconds. Default value: 2 ns . Ignored if тсом is specified.

- TFALL | TIMEFALL=value

Defines the fall time. Commutation time ' 1 ' $\Rightarrow$ ' 0 ' value. Unit is seconds. Default value: 2 ns . Ignored if тсом is specified.

- тCOM=value

Defines the commutation time. Eldo switches from the previous value to the new value with a slope of time тсом. Default is 2 ns . For backward compatibility, when тсом is specified, the parameters trise or trall will be ignored and a warning generated.

## Example: CMOS model

```
.D2A SIM=HDLA D2A_STD_LOGIC MOD=D2A_B_STD_LOGIC
.MODEL D2A_B_STD_LOGIC D2A MODE=STD_LOGIC
+ VLO=0.0 VHI=5.0 TRISE=3N TFALL=2N
+ RZ=1.0E+12 RRISE=1000 RFALL=1000
+ WEAHIGHRES=10K WEALOWRES=10K
+ LOWCAP=0.1p HIGHCAP=0.1p ZCAP=0.1p
```


## V source converter for STD_LOGIC

A type of D2A converter, FAST_STD_LOGIC, is implemented. This FAST_STD_LOGIC converter can improve simulation speed, especially when used in ADMS and ADiT. The FAST_STD_LOGIC boundary element can be applied to A2D boundaries, in this case the boundary element is equivalent to a boundary element of type STD_LOGIC.

The STD_LOGIC D2A models are very flexible; they can handle high-impedance states and signals of different strengths. However, simulation can be longer compared with a D2A acting as a voltage source, as is the case for the BIT model. The FAST_STD_LOGIC converter overcomes this limitation.

When interfacing a Verilog or VHDL Std_logic signal with analog nets, it is possible to manage conflicts of a ' $Z$ ' state with a $V$ source built-in boundary element of type FAST_STD_LOGIC which can handle only $0,1, \mathrm{X}$ and Z states.

The V source built-in boundary element can be selected by setting the mode of the converter to FAST_STD_LOGIC or STD_vSRC (they are synonymous). It has the same set of parameters as MODE=BIT Or MODE=X01 Eldo converters.

Eldo checks whether there are one or more D2A boundary elements present, which are not in a high-impedance ('Z') state. If there are, Eldo will take into account all the D2A signals on the node and will compute the resulting voltage value. This value will be imposed on the analog part as a voltage source would. This means that the voltage on that node is not an unknown to the system of equations, and this can make simulation faster. If, however, there are only highimpedance states on the D2A node, Eldo will solve for that node.

## Option DEFD2A

It is normally necessary to specify an explicit D2A between ANALOG nodes and HDL-A ports; however, with the following statement specified:
.OPTION DEFD2A=model_name
Eldo will automatically insert an implicit D2A convertor when needed. The following must be defined in the netlist:
. MODEL model_name D2A parameters
Furthermore, it is often necessary to specify MODE=BIT in the . MODEL model_name command. This is because the default for mode is x01, and very often HDL-A PORTS are of type bit, hence a resulting error mismatch in convertor type would be printed if mODe is not correctly specified.

## Example

. MODEL model_name D2A mode $=$ BIT
.OPTION DEFD2A = model_name
Additionally, these default models must be found in the netlist itself, and cannot be specified via . LIB or .ADDLIb specifications.

## Note

With the option DEFD2A, for any ANALOG node connected directly to an HDL-A OUT or INOUT port, an implicit D2A will be automatically inserted.

## Option D2DMVL9BIT

Enables direct connection between HDL-A ports of type BIT with mixed-mode nodes connected to Eldo via convertors of type MVL9 (or std_logic).

The bit type is a subset of std_logic so there is no conversion: ' 0 ' -> ' 0 ' and ' 1 ' -> ' 1 '.

## .DATA

## Parameter Sweep

```
.DATA dataname parameter_list
[+] val_list1
[+] val_list2
[+] ...
[.ENDDATA]
```

```
.DATA dataname MER[GE]| LAM[INATED]
```

.DATA dataname MER[GE]| LAM[INATED]
[+] file=filename1 param=column ... param=column
[+] file=filename1 param=column ... param=column
[+] file=filename2 param=column ...
[+] file=filename2 param=column ...
[+] ...
[+] ...
[+] [out=outfile]
[+] [out=outfile]
[.ENDDATA]

```
[.ENDDATA]
```

Two forms of .DATA statement definition are allowed. One is the inline form, and the other is where the statements are defined using external files. The data from multiple external files can be processed sequentially or in parallel.

## Parameters

- dataname

The name assigned to the .DATA statement, this name could be used in . TRAN, .DC Or . AC commands using the format: SWEEP DATA=dataname

- parameter_list

List of n parameter names.

- val_list

Set of $n$ double values corresponding to the values of the parameter_list.

- mer[GE]|LAM [INATED]

Forces Eldo to process the data statements from multiple external files sequentially (MER [GE]) or in parallel (LAM [ INATED]).

- file=filename

Definition of .DATA statements using external files. The data from multiple files can be processed sequentially or in parallel.

- param=column

Defines the column number from which the parameter values are taken.

- out=outfile

Specifies the output file in which the resulting .DATA statements can be saved.

## Notes

1. The " + " continuation characters are not required for the list of values when using this command. This differs from other Eldo commands where the " + " continuation characters are required.
2. Implicit . DAtA creation is also possible:
```
.TRAN 1n 10n SWEEP p2 3.0 4.0 1.0
```

Eldo will make two TRAN runs: one with p2 set to 3.0 , another with p 2 set to 4.0 .
3. enddata is optional.
4. Eldo will generate an ASCII output file with extension .mt\# (for transient), .ma\# (for AC) and . $m d \#$ (for a DC sweep). The \# character stands for the index of the file and a new file is created for each new .TEMP or .ALTER command.
5. It is possible to have the input signal being read from .DATA commands. An example is shown below:

```
.DATA srcname
+ time pv1
+ 00
+5n 0
+ 20n 5
.ENDDATA
V1 1 0 PWL (time,pv1)
.TRAN data=srcname
```

Here, the signal on v 1 will be read from the .DATA command. This works only if the following two conditions apply:
a. The .TRAN command is defined via a .DATA command. Time will be assumed to be the first parameter name in the .DATA command, and simulation will proceed until the last value specified in the .DATA command.
b. Both parameters which appear in the PWL must be in the same .DATA command.
6. .MPRUN can be used to take advantage of multi-processor machines for the .DATA command. Please see .MPRUN for further information.
7. SOA limits can be defined using . DATA statements. Please see .SETSOA for further information.
8. A wave defined with a a . DATA statement can be plotted with the dATA(dataname, parameter) plot specification.

## Examples

```
.TRAN 1n 10n SWEEP DATA=datatran
.DATA datatran p1 p2 p3
1.0 3.0 4.0
2.0 5.0 7.0
    .ENDDATA
```

Eldo will make two TRAN runs: the first with $p 1=1.0, \mathrm{p} 2=3.0$, and $\mathrm{p} 3=4.0$, and the second with $p 1=2.0, p 2=5.0$, and $p 3=7.0$. Note the " + " continuation characters are not required.
Here follow some examples of specifying multiple external files to be processed either sequentially or in parallel:

```
.data example1 MERGE
+ file=datal.inc col1=3 col2=2
+ file=data2.inc colA=1 colB=3
+ out=example1.inc
.enddata
```

After the first file name, the names of the columns to be created and the index where the data comes from are specified. The resulting .DATA is created using the merge of the two files:

| 1 | 2 | 3 |
| ---: | ---: | ---: |
| 4 | 5 | 6 |
| 7 | 8 | 9 |
| 10 | 20 | 30 |
| 40 | 50 | 60 |
| 70 | 80 | 90 |

The specification $\operatorname{col} 1=3 \operatorname{col} 2=2$ and $\operatorname{col} \mathrm{A}=1 \operatorname{colB}=3$ literally means: the first column is named coll and its values come from the third column of merged files; the second column is named col2 and its values come from the second column of merged files. The resulting .DATA will be:

| . DATA example1 |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
| + | coll | col2 | colA | colb |
| + | 3 | 2 | 1 | 3 |
| + | 6 | 5 | 4 | 6 |
| + | 9 | 8 | 7 | 9 |
| + | 30 | 20 | 10 | 30 |
| + | 60 | 50 | 40 | 60 |
| $+$ | 90 | 80 | 70 | 90 |
| . enddata |  |  |  |  |

The following example shows the LAMINATED specification for processing in parallel:

```
.data example2 LAM
+ file=data1.inc col1=3 col2=2
+ file=data2.inc colA=1 colB=3
+ out=example2.inc
.enddata
```

As before, the names of the columns to be created and the index where the data comes from are specified. However, unlike the merge form, values come from the original files so in this case you will notice that the resulting .DATA will be different as follows:

| . DATA | example2 |  |  |
| :--- | :--- | :--- | :--- |
| + | coll | col2 | colA |
| + | colB |  |  |
| +6 | 2 | 10 | 30 |
| +6 | 5 | 40 | 60 |
| +9 | 8 | 70 | 90 |
| .enddata |  |  |  |

## .DC

## DC Analysis

## Single Analysis

.DC

## Component Analysis

```
.DC CNAM [L|W] [TYPE nb] START STOP INCR [SWEEP DATA=dataname] [MONTE=val]
.DC CNAM [L|W] [TYPE nb] START STOP INCR
+ [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC CNAM [L|W] [TYPE nb] START STOP INCR
+ [SWEEP parameter_name start stop incr] [MONTE=val]
```


## Voltage or Current Source Analysis

```
.DC SNAM [TYPE nb] START STOP INCR [SNAM2 START2 STOP2 INCR2]
+ [SWEEP DATA=dataname] [MONTE=val]
.DC SNAM [TYPE nb] START STOP INCR [SNAM2 START2 STOP2 INCR2]
+ [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC SNAM [TYPE nb] START STOP INCR [SNAM2 START2 STOP2 INCR2]
+ [SWEEP parameter_name start stop] incr [MONTE=val]
```


## Temperature Analysis

```
.DC TEMP START STOP INCR [SWEEP DATA=dataname] [MONTE=val]
.DC TEMP START STOP INCR [SWEEP parameter_name TYPE nb start stop]
+ [MONTE=val]
.DC TEMP START STOP INCR [SWEEP parameter_name start stop incr]
+ [MONTE=val]
```


## Parameter Analysis

```
.DC PARAM PARAM_NAME START STOP INCR [SWEEP DATA=dataname]
+ [MONTE=val]
.DC PARAM PARAM_NAME START STOP INCR
+ [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC PARAM PARAM_NAME START STOP INCR
+ [SWEEP parameter_name start stop incr] [MONTE=val]
.DC PARAM PARAM_NAME [TYPE nb] START STOP INCR
```


## Data-Driven Analysis

```
.DC DATA=dataname [SWEEP DATA=dataname] [MONTE=val]
.DC DATA=dataname [SWEEP parameter_name TYPE nb start stop] [MONTE=val]
.DC DATA=dataname [SWEEP parameter_name start stop incr] [MONTE=val]
```

The .DC command activates a DC analysis, and is used to determine the quiescent state or operating point of the circuit. The operating point of the circuit is computed with capacitances opened and inductances short-circuited. A DC analysis may be requested to determine the stable initial condition of an analog circuit, prior to a transient or AC analysis. Three levels of nesting are allowed.

There are six different types of DC analysis available as shown below:

1. DC with no further parameters results in a single analysis of the circuits' quiescent state.
2. DC followed by a component name results in a variation of the element size or value. The variation sweeps from the value START to the value STOP with the incremental step INCR. The quiescent state is calculated for each incremental step.
3. DC followed by a voltage or current source, results in a voltage or current sweep of the specified source from START to STOP in increments INCR. The quiescent state is calculated for each incremental step. A second source SNAM2 may optionally be specified with associated sweep parameters. In this case, the first source is swept over its range for each value of the second source.
4. DC followed by the TEMP keyword results in a variation of temperature. The temperature sweeps from the value of START to the value of STOP with the incremental step INCR. The quiescent state is calculated for each incremental step.
5. DC followed by the PARAM keyword results in a variation of the value of a globally declared parameter PARAM_NAME. The variation sweeps from the value of START to the value of STOP with the incremental step INCR. The quiescent state is calculated for each incremental step.
6. DC followed by the parameter DATA=dataname results in a sweep of the values predefined in the .DATA command. The quiescent state is calculated for each incremental step.

Multi-threading can be activated for a single DC simulation, Eldo will share computer resources on a multi-processor machine. Alternatives are:

- command line flag -mthread (see "-mthread" on page 50) at Eldo invocation, or option mthread in the netlist. Eldo will make use of all the possible CPUs on the machine.
- command line flag -usethread \# (see "-usethread val" on page 56) at Eldo invocation, or option USETHREAD=val. This forces Eldo to use at maximum the specified (\#) number of CPU. The number specified can exceed the number of CPUs available, but this is not recommended, even though Unix will allow it.

Statistics, generated at the end of simulation, show how many CPUs have been used for the current simulation.

## Parameters

- CNAM

Name of component on which geometrical or value variations are performed. Acceptable components are inductors, resistors, MOS transistors and controlled sources (VCVS, CCVS, CCCS, VCCS). For the control sources, only the linear case is supported and only the gain of these sources may be swept.

- START

Start value of the component CnAm, voltage, temperature or current sweep. This can be specified as a parameter or as an expression.

- Stop

Stop value of the component CNAM, voltage, temperature or current sweep. This can be specified as a parameter or as an expression.

- INCR

Increment of the component, voltage, temperature, or current sweep. This can be specified as a parameter or as an expression.

- SNAM

Name of the voltage or current source which performs the DC sweep.

- temp

Keyword indicating that the temperature is to be varied.

- Param

Keyword indicating that a parameter is to be varied.

- DATA=dataname

Used in conjunction with the .DATA command. The dataname parameter should be specified using the .DATA command. Please refer to ".DATA" on page 585 for more information.

- PARAM_NAME
- Name of the globally declared parameter to be varied. Both primitive and non-primitive parameters are allowed.
- $\mathbf{L}, \mathrm{w}$

Keywords which determine if the length $\mathbf{L}$ or the width $\mathbf{w}$ of the MOS component CnAm is to be varied.

- type

Type name of the first level of variation for DC component analysis and voltage/current source analysis. Can be one of the following:

DEC
Keyword to select logarithmic variation.
оСт
Keyword to select octave variation.

## LIN

Keyword to select linear variation.

## POI

Keyword to select a list of frequency points. POI is the same as LIST except that POI expects the number of points nb to be specified as it's first argument.

- SNAM2

Name of the secondary voltage or current source for DC sweep.

- StART2

Start value of the secondary voltage or current sweep. This can be specified as a parameter or as an expression.

- STOP2

Stop value of the secondary voltage or current sweep. This can be specified as a parameter or as an expression.

- INCR2

Increment of the secondary voltage or current sweep. This can be specified as a parameter or as an expression.

- MONTE=val

Monte Carlo analysis. Equivalent to .mc val. The syntax allows a different monte value for each run. However, the actual implementation in Eldo does not account for that: it is the last monte value to be specified in the netlist which will be taken into account.

## Sweep Parameters

This section contains sweep related parameters that are previously unspecified in the Parameters section.

## - SWEEP

Specifies that a sweep should be performed on a parameter or device name.

- parameter_name

Name of the parameter or device name to sweep.

- type

Can be one of the following:
DEC
Keyword to select logarithmic variation.
ост
Keyword to select octave variation.

## LIN

Keyword to select linear variation.

## POI

Keyword to select a list of frequency points. POI is the same as LIST except that POI expects the number of points nb to be specified as it's first argument.

## INCR

Increment of the parameter or device name to sweep. (INCR can only be used when the sweep keyword is preceding it. When INCR is specified, nb is the incrementing value.)

- nb

Number of points required.

- start

Start value of the parameter or device.

- stop

Stop value of the parameter or device.

- incr

Increment of the parameter or device name to sweep.

## Note

$\qquad$
When INCR is specified as the TYPE parameter, the value which directly follows (nb) is the incrementing value. If INCR is not specified, the incrementing value (incr) must be placed after the start and stop values.

## Examples

```
vin 1 0 10
.dc vin 0 5 0.2
```

Specifies a DC analysis with voltage sweep of the voltage source vin from 0 to 5 V with an increment of 0.2 V .

```
r7 3 4 100k
.dc r7 10k 100k 10k
```

Specifies a DC analysis with resistor value variation of $\mathbf{r} 7$ from $10 \mathrm{k} \Omega$ to $100 \mathrm{k} \Omega$ with increments of $10 \mathrm{k} \Omega$.

```
r1 1 2 p1
.param p1=1k
.dc param p1 1k 10k 1k
```

Specifies a DC analysis with resistor parameter p1 variation from $1 \mathrm{k} \Omega$ to $10 \mathrm{k} \Omega$ with an increment of $1 \mathrm{k} \Omega$.

```
VIN 1 0 10
    .param p1=3
    .param pend=10
.DC VIN p1 pend 0.1
```

Specifies a DC analysis with voltage sweep of the voltage source vin from 3 to 10 V with an increment of 0.1 V . This example shows how the .Dc command accepts parameters as arguments.

```
.dc v1 dec 10 2 12 sweep r2 INCR 10 1k 100k
.dc v1 dec 10 2 12 sweep r2 1k 100k 10
```

The two lines above are equivalent. Either can be used to specify a DC analysis at each of the values for $\mathbf{v} 1$ starting at 2 V and stopping at 12 V with 10 analysis points per decade. The sweep specification will force Eldo to carry out a DC analysis on each value of $\mathbf{r} 2$ starting at $1 \mathrm{k} \Omega$ and stopping at $100 \mathrm{k} \Omega$ with an incrementing value of $10 \Omega$.

```
.dc E1 3 5 0.5
```

In the sweep of gain for linear controlled sources example above, the gain of the VCVS E1 will be swept from 3 to 5 in increments of 0.5 .

The next example shows that the DC sweep can be nested up to three levels deep. For each value of the third level variable, the second level variable is swept through its specified range. For each value of the second level variable, the first level variable is swept through its specified range. To show the order of sweepings, the below shows three independent voltage sources swept with the .DC statement.


The .PRINT statement results in the following output in the .chi file:

| V 1 | $\mathrm{~V}(1)$ | $\mathrm{V}(2)$ | $\mathrm{V}(3)$ |
| :--- | :--- | :--- | :--- |
|  |  |  |  |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $3.5000 \mathrm{E}+00$ |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |

## .DC

| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |
| :--- | :--- | :--- | :--- |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $2.5000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |
| $1.0000 \mathrm{E}+00$ | $1.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |
| $1.5000 \mathrm{E}+00$ | $1.5000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |
| $2.0000 \mathrm{E}+00$ | $2.0000 \mathrm{E}+00$ | $3.0000 \mathrm{E}+00$ | $4.0000 \mathrm{E}+00$ |

The following examples show how the keywords DEC, OCT, LIN, and POI can be specified as the type name of the first level of variation for DC component analysis and voltage/current source analysis.

```
.dc r1 DEC 8 2k 9k
.dc r1 OCT 8 2k 9k
.dc r1 LIN 100 2k 9k
.dc r1 POI 8 2k 3k 4k 5k 6k 7k 8k 9k
```


## .DCHIZ

## DC Analysis High Impedance Detection

```
.DCHIZ R=value
```

Detects high impedance values for DC analysis. All impedances higher than a user-specified value are listed. The analysis is performed just after DC analysis.

## Parameters

- $\mathbf{R}=$ value

Specifies the high impedance value. All impedances above this value will be listed.

## Example

```
V1 1 0 1.9
R1 1 2 101
R1p 2 2p 101
MC1 2p G 3 3 NMOS W=0.1u L=0.1U
R2 3 0 102
VG GP 0 1.8v
R12 GP G 100m
.param limit_value=10.1
.TRAN 10ns 1us
.PLOT TRAN V(*)
.DCHIZ R=limit_value
.MODEL NMOS NMOS LEVEL=1
```

All nodes which have an equivalent impedance higher than limit_value will be displayed and written to the .chi file, for example:

```
**** HIGH IMPEDANCE DETECTION
HIGH IMPEDANCE on node "2" Impedance = 1.010000e+02
HIGH IMPEDANCE on node "2P" Impedance = 2.020000e+02
HIGH IMPEDANCE on node "3" Impedance = 1.016275e+02
```


## .DCMISMATCH

## DC Mismatch Analysis

```
.DCMISMATCH [FILE=filename] [output] [DCALL[=0|1]]
+ [SORT_REL=value] [SORT_ABS=value] [SORT_NBMAX=value] [NSIGMA=value]
```

This command is a special form of sensitivity analysis based on statistical deviation properties of device model parameters. It computes the sensitivity of node voltages and of currents through voltage sources. All devices using a device model with statistical deviations potentially contribute to the output deviation. The aim of the .DCMISMATCH analysis is to quantify these contributions and to identify the biggest contributors to the total output deviation. It has some degree of similarity with the worst-case analysis (.wCASE). However, it will usually provide (much) less pessimistic results than worst-case analysis.
.DCmismatch will consider exclusively the dev or devx variations specified for device model parameters (in .MODEL statements) and for global parameters in the .cir file (.PARAM statements specified at the top-level, outside any subcircuit definition). The цот specifications are not taken into account.

Mismatch models try to model the inherent differences which exist between two identically drawn transistors. Each transistor behavior departs (statistically) from the nominal behavior. The deviation depends strongly on the geometry (W, L) of the transistor. Small transistors tend to be more random than large ones.
.DCmismatch produces an ASCII report in the main output (.chi) file, which lists the output deviations due to the deviations of the sensitive devices and parameters. Specifically, deviation is applied independently to the sensitive devices, and the resulting deviation of the output is computed from the RMS sum of the resulting deviations. The mismatch report can be generated in a separate file if requested.

The SORT_ parameters are used to limit the amount of output information.
The keyword, statistical $=0 \mid 1$, can be specified on X instances, device declarations, or on . subckт definitions, to specify whether any statistical variation due to DC mismatch analysis can be applied to the specified entities. If statistical is 0 , the selected devices will keep their nominal values. If statistical is 1 , the selected devices have statistical variation applied. The global default can be specified via option Statistical $=0 \mid 1$. Default is 1 .

## Note



Multiple sensitivity and statistical analyses cannot be used simultaneously. Specifically, .DCMISMATCH, .MC, and .WCASE are exclusive. Only one of them can be specified in a netlist.

DC mismatch information can also be extracted with the .EXTRACT DCM function, which returns the result for a specific label_name. It extracts the value which is dumped in the .chi file.

There are two methodologies when using the .DCMISMATCH command:

- .DCMismatch with no output specified, the analysis is performed automatically for all DC extracts (associated .EXTRACT statements required) to obtain the result.
- .dCmismatch with $V$ or I output specified, in this case, .extract dCm statements should not be specified (they are not taken into account).
Extractions using general purpose functions, such as yval, xycond, cannot be used for .DCMISMATCH analysis. Only extractions using a combination of I(device) or V(node) quantities are allowed.


## Parameters

- FILE=filename

Optional. Specifies a separate output file to be created containing mismatch results. When specified, the mismatch report will be written to both the .chi file and the file specified by this parameter.

- output

Optional. The output can be V(net_name1[, net_name2]), I(Vsrc), EXTRACT (label), or MEAS (label). If no output is specified, the analysis is performed for all DC extracts.

- DCALL [=0|1]

Optional. If set to 1 , then the . DCmismatch analysis will be performed on all points of the DCSWEEP. If set to 0 , then it will be performed only on the first one.

- SORT_REL

Only devices with a contribution to the output greater than the value:
SORT_RELX<MAX_variation_on_output> will be listed. The default value of SORT_REL is 0.001 , which means that all devices contributing to more than $1 / 1000$ of the maximum variation will be listed.

- SORT_ABS

Used to specify the absolute threshold, below which contributors will not be listed. Default value is 0 .

- SORT_NBMAX

Allows the user to limit the list of contributors to a certain value. By default, all contributors are listed.

## Note

The sorting parameters are additive, that is, their respective effects are cumulative. For example, to create a report with only devices contributing to $10 \%$ or more of the maximum output deviation and have 15 contributors at most you would specify:
SORT_REL=0.1
SORT_NBMAX=15.

- NSIGMA

Parameter used to change the default sigma value used for Gaussian distributions in Eldo statistical analysis.

The total variation on the output is computed from the 4 -sigma variation for Gaussian distribution, or from the max variation for other distributions (UNIFORM distribution or distribution defined with a .DISTRIB command). 4- sigma is the default used for Gaussian distributions in Eldo statistical analyses. This can be changed with the NSIGMA value of the .DCMISMATCH command, and if not specified, from the global option SIGTAIL=val, which defaults to 4 .

## Note

With gaussian distributions, 4-sigma deviations may cause unrealistic situations if the standard deviation is too large, so this should be handled with care. For example specifying $D E V=10 \%$ for a 0.35 V threshold voltage with a Gaussian distribution will most probably cause a problem when a -4 sigma variation is applied.

## Examples

These first two examples below show how .DCMISMATCH will consider the DEv variations specified for device model parameters and for global parameters:

```
.model nch nmos level=53 vt0=0.45 dev=1%...
```

All transistors using the nch model will be considered.

```
.param vdd=1.2V dev=5%
```

The vdd parameter will be considered.

```
.extract dc label=VS V(s)
.extract dc label=dcmm_vs dcm(VS)
.dcmismatch nsigma=1 sort_nbmax=5
```

Here Eldo will return the variation of all the valid DC extracts, namely the EXTRACT labelled VS (the second extract dcmm_vs is just for output, it will not be seen by the mismatch). The above is equivalent to the following:

```
.extract dc label=dcmm_vs dcm(VS)
.dcmismatch V(s) nsigma=1 sort_nbmax=5
```

or:

```
.extract dc label=VS V(s)
.extract dc label=dcmm_vs dcm(VS)
.dcmismatch meas(VS) nsigma=1 sort_nbmax=5
```

Below is a typical DC mismatch analysis output showing N-sigma deviation of the outputs, and a table of sorted contributors. In this example, XM2.M1 is the main contributor, and the deviation of the U0 mobility parameter of its associated .model (XM2.MOD2) is the main contributor to the XM2.M1 contribution.

```
#.DCMISMATCH V(S) SORT_REL = 1.000000e-03 NSIGMA = 1.000000e+00
Analysis results:
\begin{tabular}{llll} 
Output DC value & \(:\) & 1.7892 U & Volt \\
Total output deviation & \(:+/-14.9166 \mathrm{M}\) & Volt \\
Output deviation due to the & & & \\
contributors in the report table & : +/- 14.9166 M & Volt
\end{tabular}
Report table
-------------------------------------------
\begin{tabular}{|c|c|c|c|}
\hline \multicolumn{2}{|l|}{Output deviation
\[
7.9308 \mathrm{M}
\]} & Contributor
XM2 . M1 & Parameter \\
\hline & 5.1779 M & & M (XM2.MOD2, U0) \\
\hline & 6.0051 M & & M (XM2 . MOD2, VTH0) \\
\hline & 163.0689 U & & M (XM2 . MOD2, TOX) \\
\hline \multirow[t]{4}{*}{7.9294 M} & & XM1.M1 & \\
\hline & 5.1769 M & & M (XM1.MOD2, U0) \\
\hline & 6.0040 M & & M (XM1. MOD2, VTH0) \\
\hline & 163.0386 U & & M (XM1. MOD2, TOX) \\
\hline \multirow[t]{4}{*}{6.1906 M} & & XM7.M1 & \\
\hline & 2.5507 M & & M (XM7. MOD1, U0) \\
\hline & 5.6326 M & & M (XM7. MOD1, VTH0) \\
\hline & 302.4733 U & & M (XM7. MOD1, TOX) \\
\hline \multirow[t]{4}{*}{6.1906 M} & & XM6.M1 & \\
\hline & 2.5507 M & & M (XM6.MOD1, U0) \\
\hline & 5.6326 M & & M (XM6. MOD1, VTH0) \\
\hline & 302.4703 U & & M (XM6.MOD1, TOX) \\
\hline
\end{tabular}
```


## .DEFAULT

## Set Default Conditions

```
.DE[FAULT] TYPE VALUE
.DE[FAULT] TYPE {KEYWORD [VALUE]}
```

This command resets the default values for elements, device initial conditions and model parameters.

The first syntax shown above is the general form for resistors, capacitors, and inductors. The second syntax is the general form for other types.

You may specify only one element or model type per .Default statement. However, in your circuit netlist file you may include as many .DEFAULT statements as required to set all required default conditions.

## Parameters

- type

Type of element or model.

- KEYWORD

Any valid element or model parameter or keyword.

- value

Optional value given to keywords.

## Limitation

Eldo implementation of .Default does not support the Lossy Transmission Line (LDTL) model and IC for active devices are ignored.

## Example

## .DEFMAC

## Macro Definition

.DEFMAC MAC_NAME (ARG $\{$, ARG $\}$ ) =EXPRESSION
The . Defmac command is used to define a parameterized macro which may be instantiated (used) in the circuit netlist. The macro may contain a combination of arithmetic expressions or pre-defined Eldo functions. The macro is instantiated using the .EXTRACT command and results are listed to the ASCII output (.chi) file.

## Parameters

- MAC_NAME

Macro name.

- ARg

Argument names passed to the macro at instantiation time.

- EXPRESSION

A combination of arithmetic expressions and pre-defined function calls that may use the arguments passed to the macro.

## Note

Argument names cannot contain arithmetic operators.
Only one macro may be defined per . Defmac statement.
trise, tralle tpdxx, SLeWrate, RMS, integ, DW_A cannot be used inside .DEFMAC.
Only the so called "general purpose extraction language" terms (END, MAX, MIn, START, XAXIS, XYCOND, XUP, XDOWN, YVAL) can be used.
A macro instantiation is made by preceding the macro name with the $\$$ character.
Keywords xaxis, end and start are recognized by the .defmac statement. This simplifies the writing of macros.

## Examples

```
.defmac phmag(a, b)=xycond (a, b<0.0)-yval (a, 0.001)
.extract $phmag(vp(s), vdb(s))
```

This example defines a macro called phmag with arguments a and $b$. This macro is then instantiated via the .extract command with the arguments $a$ and $b$ being replaced by the phase voltage $\mathrm{vp}(\mathrm{s})$ and magnitude $\mathrm{vdb}(\mathrm{s})$ on node s respectively. The results are listed in the ASCII output file. The phmag macro uses the pre-defined functions xycond and yval.

[^10]```
.defmac sett(out,ratio) =
+ XYCOND (XAXIS, (out > (yval(out,END) * (1 + ratio))) ||
+ (out < (yval(out,END) * ( 1 - ratio))),END,START)
.extract sett(v(s),0.1)
```

Returns the settling time of $v(s)$, that is, the time at which $v(s)$ does not vary outside the range $0.9 \times$ final_value, $1.1 \times$ final_value, where final_value is the value of $\mathrm{v}(\mathrm{s})$ at the end of the simulation.

```
.defmac sett ( \(x\), out, tx, ratio) \(=\)
+ XYCOND (x, (out > (yval (out,tx)*(1 + ratio))) ||
+ (out < (yval(out,tx) * ( 1 - ratio))), tx, 0)
.extract \$sett(xaxis,v(s),50n,0.1)
```

This is for finding the settling time on wave out.

## .DEFMOD

## Model Name Mapping

.DEFMOD alias_model_name actual_model_name
This command can be used to map a model name in a netlist to a model name specified in a .model card. This works if the .Defmod is placed before any use of the string alias_model_name.

This is similar to the .MALIAS command, except the arguments are reversed.

## Parameters

- alias_model_name

Model name given in a netlist.

- actual_model_name

Model name defined in .model card.

## Example

$$
\begin{aligned}
& \text {. model modell } r \text { tc } 1=2 \text { tc } 2=1 \\
& \text {.defmod modalias model } \\
& \text { r1 } 0 \text { modalias } r=1 k
\end{aligned}
$$

Model name modell is aliased to modalias.

## .DEFPLOTDIG

## Plotting an Analog Signal as a Digital Bus

.DEFPLOTDIG [VTH[1]=VAL [VTH2=VAL]]
The .defplotdig command enables the user to plot an analog signal as a digital bus. This command can only be used as a precursor to VDIG of the .PLOT command.

## Parameters

- VTH[1]=VAL

If a voltage threshold is specified, the bus of an analog signal is plotted as a bus (hexadecimal format), else all the different signals of the bus are plotted separately in the wave viewer as analog waves. (VTн and vтн1 are synonymous to ensure backwards compatibility.)

- $\mathrm{vth} 2=\mathrm{VAL}$

Can be used to plot the indeterminate value, as shown below:
When only vтн1 is given:
If value $<\mathrm{VTh}$ then logic state 0 .
If value $>\mathrm{V} \boldsymbol{v} \boldsymbol{f}$ then logic state 1 .
When both vтн1 and vтнг are given:
If value < vтн1 then logic state 0 .
If VTH1 < value < VTн2 then state X.
If value $>\mathrm{V}$ тн2 then logic state 1 .

## Example

```
.DEFPLOTDIG VTH1=2.2 VTH2=2.7
.PLOT TRAN VDIG(n2)
```

When .defrlotdig is used in conjunction with .plot vdig, the signal node n2 is plotted as a digital curve and will only have values of " 1 " or " 0 ".

## .DEFWAVE

## Waveform Definition

.DEFWAVE [SWEEP] [ANALYSIS] WAVE_NAME=WAVE_EXPR
The .Defwave command is used to define a new waveform by relating previously defined waveforms and nodes. The waveform definition may contain a combination of arithmetic expressions or pre-defined functions available in Eldo. The waveform may be instantiated using the . extract command with the results being listed to the ASCII output (.chi) file or may be printed or plotted using the .PLOT and .PRINT commands.

Defwaves defined during an analysis working in complex mode (AC, NOISE, RF, and so on) are always considered complex even if they contain pure real values (in which case the imaginary part is 0.0 ). In the following example, the phase transformation is applied twice:

```
.defwave ac defwave_phase= vp(4)
.plot ac vp(4) wp(defwave_phase)
```


## Parameters

- SWEEP

When a circuit contains some .EXTRACT or .meas commands, and in the case of .STEP cards, it applies a wave operator on the curves EXTRACT=F (STEP), that is, those waves dumped in the .ext file.

- ANALYSIS

Type of analysis to be used.

- WAVE_NAME

New waveform name.

- WAVE_EXPR

Arithmetic expression relating previously defined waveforms and nodes. See "Arithmetic Functions" on page 78 for further details.

The function types PWL, PWL_CTE and PWL_LIN are also available for .DEFWAVE, see Table 10-9. They create piece-wise linear (PWL) waves which can be plotted in the binary output (.wdb) file. These functions are used for creating an ideal waveform which can then be displayed in EZwave and matched against actual simulation results. See the example in Figure $10-3$ on page 609.

## Table 10-9. PWL Function Types

| PWL(x1, y1, .. xn, yn) | Generates a piece-wise linear function. xn and yn are used to <br> calculate the equivalent output value. <br> This standard PWL function plots all specified points. |
| :--- | :--- |

## Table 10-9. PWL Function Types

| PWL_CTE $(x 1, y 1, \ldots \mathrm{xn}, \mathrm{yn})$ | Generates a piece-wise linear function. xn and yn are used to <br> calculate the equivalent output value. <br> This function plots all specified points but will hold the first <br> specified value if the simulation start time is less than the first time <br> point specified in the function. Similarly it will hold the last value <br> until the simulation is complete. |
| :--- | :--- |
| $\mathbf{P W L} \_\mathbf{L I N}(\mathrm{x} 1, \mathrm{y} 1, \ldots \mathrm{xn}, \mathrm{yn})$ | Generates a piece-wise linear function. xn and yn are used to <br> calculate the equivalent output value. <br> This function linearly extrapolates the first value using the first two <br> points of the function. The last value will also be linearly <br> extrapolated using the last two points. This will only happen if the <br> simulation start time is less than the first time value specified in the <br> function, and the simulation end time is greater than the last time <br> value of the function. |

## Notes

- Waveform definitions can be specified inside subcircuit definitions. Identical complex calculations can be performed for each instance of the subcircuit. Typically the subcircuit is declared once and instanced many times. This means there is no need to have many instances of the same subcircuit with definitions of .DEFwave and .plot for each. Eldo only calculates the .DEFWAVE statements that are called, not all . Defwave statements declared.
- Waveform names cannot contain arithmetic operators.
- Waveform names cannot contain the hierarchical separator: the period character ".".
- Only one waveform may be defined per .defwave statement.
- It is not possible to use functions which expect at least one waveform as input.
- Built-in PPL functions can not be used in Tcl procs that are called from .Defwave statements.
- A wave is instantiated by preceding the wave name w, which can be followed by a format suffix for complex waveforms, for example: wm, wdb, wp, wi, wr are enclosed in parentheses ().
- A waveform expression cannot contain a division by zero. If this is the case, $1.0 \times 10^{-15}$ is automatically assigned to a value.
- The .Defwave command is order dependent in that all components of the waveform expression must have already been defined earlier in the netlist. The following is illegal:

```
.defwave power_vdd=i(v1)*v(v1)
v1 in out ...
```

However, the following is allowed:

```
v1 in out ...
.defwave power_vdd=i(v1)*v(v1)
```

- The waveform expression must consist of waves and functions which are related to the type of analysis being performed as described in the .PLOT/PRINT commands later in this chapter. The following is illegal and will produce false results:

```
.defwave amplification=v(2)/v(1)
..
.plot ac w(amplification)
```

However, the following is allowed:

```
.defwave amplification=vm(2)/vm(1)
.plot ac wdb(amplification)
```

- The pwl function in .defwave can not be used in complex expressions. An error will be generated if the .DEFWAVE uses the function with other operators or mathematical functions. The following is not accepted:

```
.defwave tran f1 = 1 + pwl (5n,0,7n,5,8n,5,9n,1)
```

However, the following is allowed:

```
.defwave tran f1 = pwl ( 5n,0,7n,5,8n,5,9n,1)
```


## Examples

```
.defwave power_vdd=v(a)*i(vdd)
...
.extract max(w(power_vdd))
```

The example above defines a waveform power_vdd as the product of the waveforms $\mathbf{v}(\mathrm{a})$ and $i(v d d)$. The maximum value of the waveform is then extracted and listed to the ASCII output file using the .extract command.

```
.defwave w1=v(a)/v(b)
.extract integ(w(w1))
.tran 1n 100n
.plot tran w(w1)
```

The example above defines a waveform w 1 as waveform $\mathbf{v}(\mathrm{a})$ divided by waveform $\mathbf{v}(\mathrm{b})$. The integral value of the waveform is extracted and listed to the ASCII output file using the .extract command.

For more information, see ".EXTRACT" on page 637.

```
.defwave powf = 0.5*(vdip(vxx) * CONJ(I(vxx)))
-plot ac wr(powf)
```

Plots the AC power of the vxx voltage source.
Example of applying a wave operator:

```
.EXTRACT LABEL = A MAX(V(1))
.EXTRACT LABEL = B MAX(V (2))
.STEP PARAM P1 1 3 1
.DEFWAVE SWEEP my_wave = MEAS (a) + MEAS (b)
.end
```

Example using the SIGMA function to sum various items (numbers, parameters or output quantities); when items are output quantities, wildcards are accepted:

```
.EXTRACT dc SIGMA(v(*),1.0,'p1+2')
.DEFWAVE tran star3=SIGMA(ISUB(X2*.g),V(E*))
```

Example of using the pwl function:

```
v1 1 0 pwl ( 0 0 10n 10)
r1 1 0 1
.defwave tran foo = pwl(0,0,20n, meas(ex))
.extract label = ex yval(v(1),5n)
.tran 1n 10n
.plot tran w(foo)
.end
```

Example of using the PWL, PWL_CTE and PWL_LIN functions.

```
v1 1 0 pwl ( 0 0 10n 10)
r1 1 0 1
.defwave tran f1 = pwl (5n,0,7n,5,8n,5,9n,1)
.defwave tran f2 = pwl_cte(5n,0,7n,5,8n,5,9n,1)
.defwave tran f3 = pwl_lin(5n,0,7n,5,8n,5,9n,1)
.defwave tran f4 = pwl_lin(5n,0, 5n, 5)
.defwave tran f5 = pwl_lin(0n, 5)
.extract label = ex yval(v(1),5n)
.tran 1n 10n
.plot tran w(f1) w(f2) w(f3) w(f4) w(f5)
.end
```

The plot obtained from the netlist is shown in Figure 10-3. The wave $£ 4$ demonstrates how to plot vertical waves with the .Defwave command.

Figure 10-3. PWL, PWL_CTE and PWL_LIN Functions


The example below shows how waveform definitions can be specified inside subcircuit definitions. In this example, the sat curves for both devices are plotted, even though they are calculated differently.

```
.subckt nmos d g s b
m1 d g s b nmos w=10u l=1u
.defwave sat=vds(m1)-vdss(m1)
.defwave varI=(0.59*gm(m1)*gm(m1)+1.133*ids(m1)*ids(m1))*5u*1u
.ends
.subckt pmos d g s b
m1 d g s b pmos w=5u l=1u
.defwave sat=vdss(m1)-vds(m1)
.defwave varI=(0.79*gm(m1)*gm(m1)+1.589*ids(m1)*ids(m1))*5u*1u
.ends
x0 g g s b nmos
x1 d g s b nmos
x2 d g s b pmos
.plot dc w(x0.sat) w(x1.sat) w(x2.sat)
.defwave Ioffset=sqrt(w(x0.varI) +w(x1.varI)+w(x2.varI))
.plot dc w(Ioffset)
```


## .DEL

## Remove library name

.DEL LIB LIB_NAME
This command removes a library name from the nominal description. It can be used in conjunction with the .ALTER command to create modifications within the netlist before reruns.

## Example

```
v1 1 0 1
    x1 1 2 r
    r2 2 0 1
    .dc
    .extract dc v(2)
    .lib delib1.lib
    .alter
    .del lib delib1.lib
    .lib delib2.lib
    .end
```

This example demonstrates how a library file can be replaced after a first run. delib1.lib is removed and delib2.lib is put in its place.

## .DEX

```
Design of Experiments
    .DEX
+ EXPERIMENT = SCREENING | SCREENING_CTRL | SCREENING_NOISE
+ RESPONSE = LIST_OF_MEASURES
+ [DESIGN = ORTHA_2_N | ORTHA_2_2N | FULL_FACT]
+ [FACTOR = LIST_OF_FACTORS]
+ [FIND_FACTOR]
```

The Eldo command . DEx can be used to perform factor screening before attempting to solve subsequent statistical problems. The primary purpose of a variable screening experiment is to select or screen out the few important main effects from the many less important ones.

For the complete description, see the separate chapter Statistical Experimental Design and Analysis.

## .DISCARD

## Ignore Instances or Subckt Definitions

```
.DISCARD INST | SUBCKT | DEV =(name {,name})
```

This command is used to specify whether one or more subcircuits/instances/devices should be ignored during an Eldo simulation. The .DISCARD command cannot remove hierarchical instances and cannot contain wildcards.

## Parameters

- InSt

Specifies that one or more subcircuit instances will be ignored.

- SUBCKt

Specifies that all instances of the subcircuit(s) will be ignored.

- DEV

Specifies that all instances of the primitive element(s) will be ignored.

- name

The name of the instance or subcircuit that will be ignored. A list of names can be specified, in this case the brackets must be used. See Example.

## Example

In the example below the instances x 1 and x 2 and the subcircuit RESI will be ignored.

```
.SUBCKT RESI a b
R1 a b 1
.ENDS RESI
x1 1 0 RESI
x2 1 0 RESI
x3 1 0 RESI
.DISCARD INST=(X1, X2)
.DISCARD SUBCKT=RESI
```

In the example below the primitive element r 2 will be ignored.

```
*SEARCH extracted value should be -2
i1 1 0 1
r1 1 2 1
r2 1 2 1
r3 2 0 1
.discard dev = r2
.dc
.op
.extract dc v(1)
.end
```


## .DISFLAT

## Disable Flat Netlist Mode

.DISFLAT
This command is used to disable the flat netlist mode.
In the case of a large netlist, which does not use any subcircuit instances, Eldo will assume that the netlist is flat and will automatically enter into a mode where it consumes less memory for parsing the netlist. However, this mode requires that all .model statements are placed at the top of the netlist.

A message is displayed when Eldo enters this mode. Use the command .DISFlat to disable this mode.

## .DISTRIB

## User Defined Distributions (Monte Carlo)

.DISTRIB DIST_NAME (DEV1 PROB1) [\{(DEVn PROBn) \}]
This command is used to specify user defined distributions for the device tolerances DEV and цот used in Monte Carlo analysis. As such, .distrib commands are only active when the .MC command is present in the netlist causing a Monte Carlo analysis to be performed.

Different entities are able to share the same distribution. Anywhere Eldo accepts LOt/DEv specifications, you can specify LOTGROUP=group_name.

1 Please refer to ".LOTGROUP" on page 701.

## Parameters

- DIST_NAME

Name of the user defined distribution being specified.

- DEVxx

A deviance value in the range $[-1,1]$. DEvxx values must be ordered from lower to upper values. Two successive values of $\operatorname{DEVxx}$ may be equal in the case of steep distributions.

- Probxx

A probability value in the range $[0,1]$.

## .DSP

DSP (Digital Signal Processing) Computation

```
.DSP LABEL=label_name MODEL=model_name [DSP=dsp_name] waveform_name
```

Selects the waveform on which the user requires DSP to be applied.

## DSP Computation (Extended Syntax)

```
.DSP LABEL=label_name [DSP=dsp_name] waveform_name
+ [TSTART=val] [TSTOP=val] [FS=val] [NBPT=val]
+ [PADDING=val] [WINDOW=name] [ALPHA=val] [BETA=val]
+ [NORMALIZED=val] [INTERPOLATE=val] [DISPLAY_INPUT=val]
+ [FNORMAL=val] [FMIN=val] [FMAX=val]
+ [NAUTO=val] [NCORR=val] [NPSD=val] [NSECT=val]
+ [NBINTERVAL=val
+ [XSTART=val XSTOP=val SAMPLE=YES|NO FS=val]
+ [BASELINE=val] [TOPLINE=val]
+ [EDGE_TRIGGER = RISING | FALLING | EITHER]
+ [XSTART=val] [XEND=val]
```

DSP models can also be specified directly on the .DSP command, using the extended syntax, as an alternative to using .DSP in conjunction with .DSPMOD. See ".DSPMOD" on page 625 for details of the additional parameters.

## Parameters

- label_name

Label name to select which wave to be plotted (.Рцот), or on which wave quantities have to be extracted (. extract). Required.

- model_name

The name of the computational model, defined in the .DSPMOD command, to apply on the wave specified by waveform_name. model_name must be a valid .DSPMOD label.
Required.

- dsp_name

Specifies the correlogram, periodogram, histogram, or frequency method.

- waveform_name

Any regular Eldo waveform name: there can be any number of .DSP commands specified in the .cir file.

## Examples

```
.DSP LABEL=LBL1 MODEL=PSD_CORRELO V(1)
.DSP LABEL=LBL2 MODEL=PSD_PERIODO W('v(2)+v(4)')
```

These DSP commands define two new PSD entities named LBL1 and LBL2. LBL1 is obtained by applying a DSP model PSD_CORRELO on wave $\mathrm{V}(1)$. LBL2 is obtained by applying a DSP
model PSD_PERIODO on wave $V(2)+V(4)$. PSD_CORRELO and PSD_PERIODO must be defined by a .DSPMOD command.

Display and .EXTRACT of DSP results:

```
[.PLOT|.PRINT|.PROBE ] DSP DSPxx(label_name)
.EXTRACT DSP <expression>
```

where xx stands for $\mathrm{DB}, \mathrm{R}, \mathrm{I}, \mathrm{P}, \mathrm{M}$.

```
.DSP LABEL=LBL2 MODEL=PSD_PERIODO V(1)
.PLOT DSP DSPDB(LBL2)
```

It is also possible to extract values from a DSP waveform:

```
.DSP LABEL=LBL1 MODEL=PSD_CORRELO V(1)
.PLOT DSP DSPDB(LBL1)
.EXTRACT DSP YVAL(DSPDB(LBL1),5MEG)
```

Eldo will print out the value (in dB ) at 5 Meg for the DSP done on $\mathrm{V}(1)$.
The following is an example of the extended syntax, the following line:

```
.DSP LABEL=FOO DSP=FREQUENCY XSTART=20n XSTOP=100n v(out)
```

is equivalent to the Frequency Computation .DSPmod example:

```
.DSPMOD LABEL=FMOD DSP=FREQUENCY XSTART=20n XSTOP=100n
.DSP LABEL=FOO MODEL=FMOD v(out)
```


## .DSPF_INCLUDE

## Load DSPF File

```
.DSPF_INCLUDE [FILE=]DSPF_FILENAME [INST={list_of_subckt_inst}]
+ [LEVEL=C|RC|RCC] [DEV=SCH[EMATIC]|DSPF] [RMINVAL=val] [CMINVAL=val]
+ [CCMINVAL=val] [ADDXNET] [ADDX] [MSUFFIX=string]
.DSPF_INCLUDE [FILE=]DSPF_FILENAME [LEVEL=C|RC|RCC]
+ [DEV=SCH[EMATIC]|DSPF] DEDICATEDX=subckt_name [RMINVAL=val]
+ [CMINVAL=val] [CCMINVAL=val] [ADDXNET] [ADDX] [MSUFFIX=string]
```

By specifying this command inside a netlist, Eldo will add the parasitic elements described inside the specified DSPF (Detailed Standard Parasitic Format) file.

Use the option MAX_DSPF_PLOT=val ("MAX_DSPF_PLOT=VAL" on page 1003) to override the maximum number of DSPF interface nodes plotted. By default, this limit is 100 .

Use option KEEP_DSPF_NODE ("KEEP_DSPF_NODE" on page 1002) to force Eldo to keep the original .РLот/.probe command if a node coming from the DSPF has the same name. When a node is replaced by a parasitic net using a DSPF file, this node can be renamed or even removed from the design.

The inst and dedicatedx specifications are mutually exclusive.
See also commands .IGNORE_DSPF_ON_NODE and .SELECT_DSPF_ON_NODE for additional control over which nodes should be ignored or selected for parasitics.

Specify option COLLAPSE_DSPF_OUTPUT ("COLLAPSE_DSPF_OUTPUT [=@|\#]" on page 999) to force Eldo to regroup currents (I, Ix, Isub) and noise outputs according to the device or subckt instance specified in arguments. By default the DSPF character is set to @.

## Parameters

- DSPF_FILENAME

Name of the DSPF file. This parameter must be the first specified on the command line. FILE= is optional.

- INST

Specifying this parameter will force Eldo to only include the parasitic elements for the specified subcircuit instances given in list_of_subckt_instances. It will assume that the DSPF file is hierarchical.

- Level=C|RC|RCC

Defines the level of parasitics to use from the specified DSPF file. This can also be specified using option DSPF_LEVEL (see "DSPF_LEVEL=C $\mid$ RC $\mid$ RCC" on page 976 for more information). Local filter of the DSPF file, level can be:
c-backannotation of total (lumped) net capacitance contained in the DSPF file

RC-backannotation of distributed R/C/L contained in the DSPF file, ignoring floating capacitors

RCC-backannotation of any distributed R/C/CC/L/K contained in the DSPF file (default)

- DEV=SCH[EMATIC]|DSPF
sch [ematic] specifies the DSPF file contains only the parasitics. Default.
DSPF specifies the DSPF file contains both the parasitics and the intentional devices. Sometimes it is more accurate to have the extractor generating a file containing both. For this sort of file, .SELECT_DSPF_ON_NODE and .IGNORE_DSPF_ON_NODE are ignored.
When Dev=DSPF is specified, Eldo will take three actions:
- Eldo will include the file specified in the command as if it was a . Lib command. Eldo will therefore have two variants of the same subcircuit in its database, one corresponding to the intentional devices which should be present in the circuit, and another one included by the .DSPF_INCLUDE command, corresponding to the version with its parasitics.
- Eldo will emulate a .BIND command on the instances/subcircuits which are specified on the .DSPF_INCLUDE command.
- Eldo will apply filters, if any, to the DSPF devices.

Generally, the number of pins and the pin order given in the . Subckt found in the DSPF file differs from the list in the intentional design. Eldo will check for pin names in both intentional and DSPF subcircuit to ensure proper connection, based on node name.

If the DSPF version contains more pins than the intentional, then it is assumed that these pins correspond to global nets, and Eldo will make map as such. Errors will be issued if no such global name can be found. Note that the index of the pin in the IX or VX plot command refers to the index of the intentional design.

- RMINVAL

Specifies the minimum resistance of a resistor, in $\Omega$. Resistors with a value less than the specified minimum value are removed from the netlist and replaced by short circuits. The default value is $-\infty$.

- CMINVAL

Specifies the minimum value of a grounded capacitor, in Farads. Grounded capacitors with a capacitance of less than the specified minimum value are removed from the netlist. The default value is $-\infty$.

- ccminval

Specifies the minimum value of a floating capacitor, in Farads. Floating capacitors with a capacitance of less than the specified minimum value are removed from the netlist. The default value is $-\infty$.

## Note

The reason for the $-\infty$ defaults (instead of zero) is to take into account the possibility of negative resistances.

- ADDXNET

Keyword instructing Eldo to insert an X character on hierarchical names specified in the DSPF file for retrieving the node in the pre-layout design (where X is added as necessary). This addition of the X character is used only for the ${ }^{*}$ NET instructions. For an example, see "Example 3" on page 624.

## - ADDX

Keyword instructing Eldo to insert an X character on hierarchical names specified in the DSPF file for retrieving the node in the pre-layout design (where X is added as necessary). This addition of the $X$ character is used only for both $* \mid$ NET and $* \mid I$ instructions. There is no flag specifically for just *|I instructions.

- MSUFFIX=string

Can be specified to handle situations where a device in the nominal design is split into different devices in the DSPF. Usually MSUFFIX is the "__" or the "@" string. The use of the string depends on the value specified for DEV.

- DEV=SCHEMATIC

In this mode, the DSPF file contains only the parasitics ( $\mathrm{R}, \mathrm{L}, \mathrm{C}$ devices), which will be added to the nominal design.

```
* NET N$26 7.87008e-14
* I (X_X2:minus X_X2 minus B 0.0 49.165 301.725)
* I (X_X14:g X_X14 g I 0.0 55.38 255.93)
* I (X_X14__2:g X_X14__2 g I 0.0 55.38 277.71)
```

It can happen that the nominal design contains only one instance (such as X_X14 in the example above), while in the DSPF this device is split in several devices, and the name of these devices is built by catenating to the nominal name a predefined string, which is usually "__" or "@", followed by an index.

For instance, X_X14__2 in the example above derives from X_X14.
By default, Eldo will complain that it is not able to retrieve the devices with the extensions, and for sake of security does not apply any DSPF insertion on the node. But if MSUFFIX is set, Eldo will handle this situation by simply connecting the nodes which appear in the extended devices to their counterpart in the nominal device.

With the example above, Eldo will connect X_X14__2:g to the node X_X14:g and will process the DSPF accordingly.

This means that Eldo will re-catenate the devices, hence simplifying the DSPF topology.

- DEV=DSPF

In this mode, the DSPF file contains both the nominal devices and the parasitics. The only problem here is a problem of printout, as illustrated below:

X_X24 X_X24:PLUS X_X24:MINUS VMINUS RPO1PM1 R=533.401 w=4e-06 NC=11 lpe=3
X_X24@3 X_X24@3:PLUS X_X24@3:MINUS VMINUS RPO1PM1 R=533.401 w=4e-06 NC=11

+ lpe=3
X_X24@2 X_X24@2:PLUS VMINUS VMINUS RPO1PM1 R=533.401 w=4e-06 NC=11 lpe=0
if there is a printout such as .PLOT IX(X_X24.1), then results will not be correct since the output will not take into account the current flowing devices X_X24@3 and X_X24@2.

Therefore, if MSUFFIX is set to "@", then Eldo will recognize that X_X24@3 and X_X24@2 do derive from X_X24 (X_X24 must appear first in the DSPF files, and the 'child' must follow), and Eldo will then replace the 3 X lines above by the statements:

```
X_X24 X_X24:PLUS X_X24:MINUS VMINUS RPO1PM1 R=533.401 w=4e-06 NC=11 lpe=3
M = 3
.connect X_X24:PLUS X_X24@3:PLUS
.connect X_X24:PLUS X_X24@2:PLUS
.connect X_X24:MINUS X_X24@3:MINUS
.connect X_X24:MINUS X_X24@2:MINUS
```

This means that when MSUFFIX is set, corresponding devices are merged again into a single device with the proper M factor value. This means that DSPF is simplified, but output commands are providing correct results. Note that with the scheme above, in case of mismatch of parameters between nominal and subsequent instances, Eldo will take the parameter values of the nominal statement: warning will be then displayed.

- DEDICATEDX=subckt_name

The specified DSPF file, will only be used for the dedicated instance subckt_name. Eldo will assume that the . SUвскт command is not specified in the DSPF file and that the node name in the DSPF file refers to the node names local to the dedicated instance name. Without the option Eldo will assume that the nodes/objects in the DSPF are the top level nodes/objects.

In DSPF files, it is common not to specify the x on subcircuit names that are referenced in the file. When Eldo cannot find a NET name (in *|NET command), Eldo will check whether the NET exists with the letter $x$ specified. If the node is found, Eldo will assume that the $x$ was meant for all node names in the DSPF file.

If the contents of the DSPF file are:

```
.subckt top IN OUT
* NET TOP/net1 0.827ff
* I (TOP/1/M1:D TOP/1/M1 D O 0ff)
* I (TOP/1/M2:D TOP/1/M2 D O 0ff)
* I (TOP/2/M1:G TOP/2/M1 G I 0.070ff)
* I (TOP/2/M2:G TOP/2/M2 G I 0.105ff)
R1 TOP/1/M1:D TOP/net1:1 100
```

and the contents of the .cir file are:

```
.subckt top in out
XTOP in out inv2
.ends
V1 in 0 pulse( 0 2 1p 100p 100p 5n 10n)
C1 out 0 1f
X1 in out top
```

Eldo will not find the node x1.top.net1. Therefore, Eldo will look for x1.xtop.net1, which will be found. Eldo will now assume that the letter x should be used for all the nodes in the DSPF. Eldo will now assume that the instruction:

```
R1 TOP/1/M1:D TOP/net1:1 100
```

should be:

```
X1.XTOP.NET1_R1 X1.XTOP.X1.M1:D X1.XTOP.NET1:1 100
```


## Connecting a source to a DSPF back-annotated node

It is possible to connect a source to a node that is back-annotated with DSPF. This might be useful to insert a voltage or current source to a specific node to check a critical path. However, after DSPF extension, the original node might be expanded in several nodes, and there might be no path remaining between the extra source and the network, that is, the extra source no longer has a connection to the network. This is because the extra source was not in the design when DSPF information was created. The solution is that nodes connected to that extra source are not expanded by DSPF. Eldo can detect such situations when the extra source is instantiated from the top of the design and connected to a node at a lower level of hierarchy, using the full node pathname. For example:

```
.SUBCKT INV in out
R1 in internal 1k
.ends
X1 in out INV
v1 X1.internal 0 5 !full pathname usage
```

Eldo will detect this configuration, and DSPF instructions will be ignored on node X1.internal. This is similar to the command: .IGNORE_DSPF_ON_NODE X1.internal.

However if the extra source is added at the same level as the nodes (for example all at the top), Eldo will only be able to issue a message that the node is connected to a single device only, and
will indicate that there is a possible DSPF connection problem. The user must then manually add the command .IGNORE_DSPF_ON_NODE on that node in order to deal with that specific situation.

## Related Commands

. IGNORE_DSPF_ON_NODE, see ".IGNORE_DSPF_ON_NODE" on page 684, .MAP_DSPF_NODE_NAME, see ".MAP_DSPF_NODE_NAME" on page 705, .SELECT_DSPF_ON_NODE, see ".SELECT_DSPF_ON_NODE" on page 862.

## Example

This example (see test_dspf.cir netlist below) can be run with and without the following line to compare the simulation results with or without the parasitics effects:

```
.dspf_include testspf2.spf
```

Inside this example, when the DSPF is included, the node $\operatorname{XTOP}$. net 1 is replaced by a network of resistors, so, according to the DSPF file, the node itself does not exist anymore, but is replaced by three different nodes: XTOP.net1:1, XTOP.net1:2, XTOP.net1:3. In this case, the plot statement: .plot tran $\mathbf{v}$ (in) $\mathbf{v}$ (out) must be replaced by .probe tran $\mathbf{v}$ (XTOP.net1*) to plot all the nodes "composing" the original node XTOP.net1.

File test_dspf.cir (located in \$MGC_AMS_HOME/examples/eldo/):

```
* test DSPF
.dspf_include testspf2.spf
.global vdd gnd
.subckt inv a y
+ln=2e-07 wn=2.8e-07 lp=2e-07 wp=2.8e-07
M1 Y A vdd vdd EPLLMM9JU w=wp l=lp m=1
M2 Y A gnd gnd ENLLMM9JU w=wn l=ln m=1
.ends
.subckt inv2 a y
X1 a net1 inv ln=0.18u wn=2.0u lp=0.18u wp=4.0u
X2 net1 y inv ln=0.18u wn=2.0u lp=0.18u wp=4.0u
.ends
V1 in O pulse( 0 2 1p 100p 100p 5n 10n)
C1 out 0 1f
XTOP in out inv2
VDD vdd 0 2
VGND gnd 0 0
.plot tran v(in) v(out)
*.plot tran v(XTOP.net1)
.probe tran v(XTOP.net1*)
.tran 1n 20n
```

```
.model EPLLMM9JU PMOS level=53 rd=100 rs=100
.model ENLLMM9JU NMOS level=53 rd=80 rs=80
.end
```

File testspf2.spf:

```
* DSPF 1.0
DIVIDER /
DELIMITER :
GROUND_NET VSS
NET XTOP/net1 0.827ff
I (XTOP/X1/M1:D XTOP/X1/M1 D O 0ff)
I (XTOP/X1/M2:D XTOP/X1/M2 D O 0ff)
I (XTOP/X2/M1:G XTOP/X2/M1 G I 0.070ff)
* I (XTOP/X2/M2:G XTOP/X2/M2 G I 0.105ff)
R1 XTOP/X1/M1:D XTOP/net1:1 100
R2 XTOP/X1/M2:D XTOP/net1:1 100
R3 XTOP/net1:1 XTOP/net1:2 2000
R4 XTOP/net1:2 XTOP/net1:3 2000
R5 XTOP/X2/M1:G XTOP/net1:3 100
R6 XTOP/X2/M2:G XTOP/net1:3 100
C1 XTOP/X2/M1:G VSS 1.53ff
C2 XTOP/X2/M2:G VSS 1.71ff
C3 XTOP/net1:1 VSS 2.80ff
C4 XTOP/net1:2 VSS 2.80ff
C5 XTOP/net1:3 VSS 2.80ff
.END
```

Parasitic resistor values have been multiplied by 1000 in order to display a real DSPF loading impact on the results.

## Example 2

When the DSPF file does not contain the . subcкт command, for example:

```
dedicated_example.spf
* NET TOP/net1 0.827ff
```

and the .cir file contains:

```
.SUBCKT top in out
XTOP in out inv2
.ENDS
V1 in 0 pulse( 0 2 1p 100p 100p 5n 10n)
C1 out 0 1f
X1 in out top
```

.DSPF_INCLUDE dedicated_example.spf DEDICATEDX=X1

Specifying dedicatedx=x1, the node $\boldsymbol{T}$ op in the DSPF file will refer to the node $\mathbf{x 1 . t o p}$ in the .cir file, that is, node IN.

## Example 3

Naming in DSPF files can vary from one extractor to the next. In particular, node names specified in the $* \mid$ NET instructions and device names specified in the $* \mid$ instructions may or may not contain the letter X in names.

For instance, inside the DSPF could be:

* NET I117/net18 0.00415015 PF
* I (XI117/XM26:D XI117/XM26 D B $0 \quad 62.255$ 143.84)
* I (XI117/XM31:D XI117/XM31 D B $0 \quad 67.595$ 146.295)

This means that on $* \mid$ NET is XI117/net18, while on the *|I instance naming is correct from the Eldo point of view.

Setting keyword parameter ADDXNET instructs Eldo to insert an X character on hierarchical names specified in the DSPF file for retrieving the node in the pre-layout design (where X is added as necessary).

## .DSPMOD

```
PSD (Power Spectral Density) Computation
.DSPMOD DSP=CORRELO|PERIODO LABEL=label_name
+ [TSTART=val] [TSTOP=val] [FS=val] [NBPT=val]
+ [PADDING=val] [WINDOW=name] [ALPHA=val] [BETA=val]
+ [NORMALIZED=val] [NORMALIZATION_FACTOR=val] [INTERPOLATE=val]
+ [DISPLAY_INPUT=val] [FNORMAL=val] [FMIN=val] [FMAX=val]
+ [NAUTO=val] [NCORR=val] [NPSD=val] [NSECT=val]
```

For PSD parameter descriptions, please see "PSD Computation Parameters" on page 626. For details on the principles of PSD computation, see Power Spectral Density in the EZwave User's and Reference Manual.

Two methods are available for calculating this quantity. The Correlogram Method means that the FFT is used directly to compute estimates of the PSD function $\boldsymbol{\operatorname { R x x }}(\boldsymbol{n})$ for $\boldsymbol{N}_{\text {auto }}$ lags, where $2 \times \boldsymbol{N}_{\text {auto }}$ is the size of the transform used. The Periodogram Method means that a sliding FFT is used to compute estimates of the PSD directory rather than estimating a PSD function.

## Histogram Computation

```
.DSPMOD DSP=HISTOGRAM LABEL=label_name NBINTERVAL=val
+ [XSTART=val XSTOP=val SAMPLE=YES|NO FS=val]
```

Generates a histogram of the input wave showing the wave's magnitude probability density distribution. The input wave is first sampled to equidistant points if the optional argument SAMPLE was set.

For Histogram parameter descriptions, please see "Histogram Computation Parameters" on page 628.

## Frequency Computation

```
.DSPMOD DSP=FREQUENCY LABEL=label_name
+ [BASELINE=val] [TOPLINE=val]
+ [EDGE_TRIGGER = RISING | FALLING | EITHER]
+ [XSTART=val] [XEND=val]
```

Provides access to the frequency measurement of EZwave. It returns the instantaneous frequency of a signal. The measurement is not performed by Eldo, the default values for the parameters are defined by EZwave. Using this DSP function forces the use of the JWDB server, even if JWDB output has been disabled.

For Frequency parameter descriptions, please see "Frequency Computation Parameters" on page 629.

There can be any number of .DSPMOD commands specified in the .cir file.
A more compact syntax is also available. It allows to define the model parameters directly on the .DSP command, without the need for a separate .DSPMOD statement. For example, the following line is equivalent to the Frequency Computation Example:

```
.DSP LABEL=FOO DSP=FREQUENCY XSTART=20n XSTOP=100n v(out)
```

See ".DSP" on page 615 for more details.

## PSD Computation Parameters

- DSP=CORRELO|PERIODO

Specifies either the correlogram or periodogram method.

- LABEL

Defines the name of the computational model, which will then be selected in the .DSP command to be applied to a specific input signal. Required.

- tStart

Time value from which the time window will start.

- TSTOP

Time value that specifies the end of the time window.

- FS

Sampling frequency.

- NBPT

Number of sampling points to be used in the time window.
These parameters satisfy the following equation:

$$
\frac{N b p t-1}{F s}=\text { Tstop }- \text { Tstart }
$$

- PADDING

Specifies that padding zeros before or after the signal can be added.
$0=$ No padding
$1=$ Zeros are added at the beginning of the FFT input window
$2=$ Zeros are added at the end of the FFT input window (default)
$3=$ Zeros are added evenly at the beginning and at the end of the FFT input window.

- window

Specifies the Sampling Window to be used. The following parameters are allowed: rectangular (default), parzen, bartlett, welch, blackman, blackman7, klein, hamming, hanning, KAISER, DOLPH_CHEBYCHEV.
i
For further details, please see the EZwave User's Manual.

- ALPHA

Used when the window is dolph_chebychev or hanning.

- beta

Used when the window is KAISER. Constant which specifies a frequency trade-off between the peak height of the side lobe ripples and the width of energy in the main lobe.

- NORMALIZED

Specifying 1 means that all the points of the result are multiplied by $2 /$ nвpr. Default.
Specifying 0 means no normalization of the results.

- normalization_factor

Replaces the default factor ( $2 / \mathrm{NBPT}$ ) which is applied to FFT results when normalized is set to 1 . It is ignored if normalized is set to 0 .

- interpolate

Sets type of interpolation:
$0=$ No interpolation (default)
$1=$ Linear interpolation
$2=$ Cubic Spline interpolation
3 = Blocker Sampler interpolation

- display_INPut

Allows visualization of the transient window used as input of the PSD: this waveform contains equally-spaced time value points.
$0=$ do not display PSD input (default)
$1=$ display PSD input (if output is displayed)

- fnormal

Adjusts the results around the Y -axis so that the point for the specified frequency is 0.0 .

- fmin

Starting frequency used inside the result window.

- fmax

Last frequency used inside the result window.

- NAUTO

Number of points for the autocorrelation result.

- NCORR

Number of autocorrelation points used for the PSD computation.

- NPSD

Number of points for the PSD result.

- nSECT

Number of points for each section. Can only be specified if the periodogram method is specified (DSP=PERIODO).

## PSD Computation Examples

```
.DSPMOD DSP=CORRELO LABEL=PSD_CORRELO
+ TSTART = 200n
+ TSTOP = 400n
+ NORMALIZED = 0
+ INTERPOLATE=0
+ DISPLAY_INPUT=1
```

This DSP model command defines a set of parameters for a PSD computation using the correlogram method. Input values will be sampled from 200 ns to 400 ns . Default value for number of sampling points (NBPT) is 1024. Output signals will not be normalized and the PSD input signal will be dumped in the output file.

```
.DSPMOD DSP=PERIODO LABEL=PSD_PERIODO
+ TSTART = 0
+ TSTOP = 1.93e-8
+ NBPT = 100
+ NORMALIZED = 0
+ INTERPOLATE=0
+ DISPLAY_INPUT=1
+ FS=5.12e9
+ ALPHA=0.5
```

This DSP model command defines a set of parameters for a PSD computation using the periodogram method. The input signal has 100 points, sampled between 0 and 19.3 ns .

## Histogram Computation Parameters

- DSP=HISTOGRAM

Specifies the histogram method.

- LABEL

Defines the name of the computational model, which will then be selected in the .DSP command to be applied to a specific input signal. Required.

- NBINTERVAL

Specifies the number of intervals which will be used to compute the distribution.

- xstart

X value from which the measurement window will start.

- XSTOP

X value from which the measurement window will stop.

- SAMPle

If YES, perform a sampling of the input wave (default is NO).

- FS

Sampling frequency.

## Histogram Computation Example

```
.DSPMOD DSP=HISTOGRAM LABEL=HISTO1 NBINTERVAL=10
+ XSTART=3n XSTOP=END SAMPLE=YES
    .DSP label=s_histo model=HISTO1 v(1)
    .PLOT dsp dsp(s_histo)
```

This DSP model command defines a set of parameters for a histogram computation, labelled HISTO1. The measurement window is between 3 ns and the end of the simulation, with sampling performed on the input signal. The resulting histogram contains ten intervals.

## Frequency Computation Parameters

- DSP=FREQUENCY

Specifies the frequency method.

- LAbel

Defines the name of the computational model, which will then be selected in the .DSP command to be applied to a specific input signal. Required.

- baseline

Y-value that sets the low threshold of the signal. If baseline is not provided then this value will be computed.

- topline

Y-value that sets the high threshold of the signal. If topline is not provided then this value will be computed.

- EDGETRIGGER=RISING|FALLING|EITHER

Type of edge used for the calculation of the frequency. If EITHER is specified, there will be no difference made between rising and falling edges.

- XSTART
$X$ value at the beginning of the measurement interval. If the $X$ value is not provided then the X start of the input signal will be used.
- XSTOP
$X$ value at the end of the measurement interval. If the $X$ value is not provided then the $X$ end of the input signal will be used.


## Frequency Computation Example

```
.DSPMOD LABEL=FMOD DSP=FREQUENCY XSTART=20n XSTOP=100n
.DSP LABEL=FOO MODEL=FMOD v(out)
```

This DSP model command defines a set of parameters for a frequency computation. The measurement window is between 20 ns and 100 ns .

## .END

## End Eldo Netlist

.END
This command terminates the simulator input description. Any text which follows it is ignored, unless there is another .END statement; in which case, all lines between the preceding .END and the current .END will be considered as another circuit to simulate. This enables the possibility to have several circuits in the same netlist file.

For multi-circuit simulations, Eldo simulates all the circuits contained inside the input files; the .END statement is optional inside the first circuit, but it must be specified inside the subsequent circuits.

## Example

```
first title
.end
second title
    .end
```

The line following the .end statement is the title of the next circuit.

## .ENDL

## End Eldo Library Variant Description <br> .ENDL

This command terminates a library variant description. Any text which follows it is ignored.
(1) See "Library variant management" on page 694 for details.

## .ENDS

## End Eldo Subcircuit Description <br> .ENDS

This command terminates an Eldo subcircuit description. Any text which follows it is ignored.
$\qquad$

## .EQUIV

## Replace Node Name for Display

```
.EQUIV new_name=netlist_name
```

This command is used to change the name of a netlist node to a new display name. The new name can then be used in display output statements such as .Рцот and .extract. Both the original name and the new name will be valid. The name can be a hierarchical name.

## Parameters

- new_name

New name of node for display.

- netlist_name

Node name to be changed.

## Examples

This is a full netlist using the .equiv command:

```
equiv
    .sigbus B[3:0] vhi=2.5 vlo=0 trise=0.1n tfall=0.1n base=hexa
+ 0n A
+ 10n 3
+ 20n 4
+ 30n 8
+ 50n F
r0 B[0] 0 1k
r1 B[1] 0 1k
r2 B[2] 0 1k
r3 B[3] 0 1k
.tran 1n 60n
.equiv enable=b[0]
.equiv xin.out=b[1]
.probe
.plot tran v(enable)
.plot tran v(xin.out)
```

From the above netlist, the following two lines change the names of the nodes $\mathrm{b}[0$ ] and $\mathrm{b}[1]$ to enable and xin.out. The name can be anything the user chooses.

```
.equiv enable=b[0]
.equiv xin.out=b[1]
```

From the above netlist, the . Рцот command uses the new node names, v(enable) and v (xin.out). These names will be the names displayed in the waveform viewer after the simulation is carried out.

```
.plot tran v(enable)
.plot tran v(xin.out)
```

The following example uses the .EQuIv command with a voltage source node:

```
v1 vss 0 5
.tran 10n 100n
.equiv vin=vss
.plot tran v(vin)
```

The following example show how the new name can be a hierarchical name:

```
.EQUIV XBUF.IN = NET$34
.PLOT TRAN V(XBUF.IN)
```


## .EXTMOD

## Extract Mode

.EXTMOD FILE=filename
The . EXTRACT commands are merged with the simulation itself. In some cases, this causes a lot of wasted CPU time. If the user makes a mistake when specifying the .EXTRACT command, the command must be fixed, then the simulation itself re-run to obtain the correct results. When the simulation takes a few seconds, this is not a problem. When the simulation takes a few hours of CPU, this is of course a big problem.

Use the . Ехтmod command to perform only the .ехтRACt commands, without performing the simulation(s). Eldo will decorrelate the 'simulation' from the 'extraction'. See ".EXTRACT" on page 637 for more information.

This may cause large output files. Eldo automatically identifies the waveforms used in .EXTRACT/.meas statements and save them to the file. This is preferable to being forced to rerun hours of CPU because the wrong . Еxtract formula was entered.

This functionality can also be specified with the command line argument -extract filename, see "-extract filename" on page 47.

## - filename

Name of an EZwave . $w d b$ output file. Required. The extractions in the netlist will be solved using the waves contained in this file.

## .EXTRACT

## Extract Waveform Characteristics

```
.EXTRACT [EXTRACT_INFO] [LABEL=NAME] [FILE=FNAME] [UNIT=UNAME] [VECT]
+ [CATVECT] $MACRO|FUNCTION [OPTIMIZER_INFO] [MC_INFO] [TIME=VALUE]
+ [INTERP_MODE=LINEAR|QUADRATIC|SAMPHOLD|HISTOGRAM|SPECTRAL]
```

This command extracts waveform information using a combination of arithmetic expressions or pre-defined functions. A flexible language exists in Eldo to extract characteristics from raw simulation results (for example the maximum value of a waveform, or the time at which a given threshold is crossed by a waveform, and so on). The type of analysis for which the specified extraction is carried out may be defined. This is useful when different types of analyses are performed in the same simulation run.

The results are listed to the ASCII output (.chi) file. They can also be written to a specified file fname.aex when option aex is specified in the netlist. Use the option alignext to specify Eldo to write tabulated .EXTRACT results in the .aex file. By default the results are not tabulated (aligned).

The . РLOT command may also be used to plot extraction results. It is used to specify which simulation results have to be kept by the simulator for graphical viewing and post-processing. See ".PLOT" on page 791.

When extraction statements are combined with parameter sweeping statements (see ".STEP" on page 890), Eldo automatically creates waveforms showing the extraction results versus the swept parameter. For example, a user may extract the width of an output pulse from a transient simulation, and sweep the power supply level. In this case Eldo will automatically create a waveform showing the width of the pulse versus the power supply level. Similarly, if extractions and .ALTER statements are combined, Eldo will automatically create waveforms showing the extraction results versus the index of the .ALTER runs (see ".ALTER" on page 549). In this case, the $X$ axis will contain $1,2,3$, and so on. The initial display in the viewer can also be prepared using .Рцот commands (see the .Рцот ехтract... description, "EXTRACT" on page 798). Example:

```
.EXTRACT TRAN label=VMAX MAX(V(out))
.PARAM powersupply=1.2
VDD VDD 0 'powersupply'
.STEP PARAM powersupply list 1.2V 1.3V 1.4V 1.6 2V
.PLOT EXTRACT meas(VMAX) ! this will create a waveform
* showing VMAX(powersupply)
```

By default, the extraction waveforms, generated by a .ЕXTRACT combined with a sweep (.TEMP, . STEP, or .ALTER), are saved inside the $E X T$ folder in the main . $w d b$ file, which can be read by EZwave.

To save single datapoint extract results (for example, scalars) in the .wdb file, so that they can be compared between . $w d b$ files, use option DUMP_EXTRACT.

It is also possible to extract values from an FFT waveform. Additionally, in the case where a set of simulation runs were done with a parameter $(\mathrm{P})$ being varied, and a given output ( O ) extracted, users may wish to extract a value based on the obtained $\mathrm{P} / \mathrm{O}$ curve.

It is always preferable to insert any .extract commands at the end of the netlist, since they can refer to objects (such as voltage sources) which need to be defined beforehand.

If you make a mistake when specifying a .EXTRACT command then you can correct the offending command and re-invoke Eldo using the -extract flag (eldo <netlist.cir> -extract). This will only re-run the .EXTRACT commands in the netlist without performing the simulation(s), see "-extract filename" on page 47 for more information. This is especially useful for simulations that take a considerable amount of time. This functionality can also be specified using the command .Extmod, see ".EXTMOD" on page 636 for more details.

There are special extensions to the .EXTRACT command for the purpose of optimization.

For more information see the Optimizer in Eldo chapter.

Extract accessor functions, extract(), meas (), or initial_extract () can be used in .EXTRACT statements to perform an "extract of extract", see "Extract accessor functions" on page 643.

To compare an extracted wave to a reference specify the UNIT parameter to define the unit of the extract. By default EZwave displays separate axes. This can be used when plotting the extract wave during a sweep analysis.

If a .EXTRACT command is present inside a .ALTER command, an EXT folder will be created in the.$w d b$ file on the condition that the .EXTRACT statement remains unchanged for each . ALTER file. If this condition is not met, the EXT folder is not created. For further details, see ".ALTER" on page 549.

You can use wildcards in .extract commands. For example:

```
.extract tran max(v(*))
.extract tran yval(v(x*.[1-9]*),20n)
.extract tran yval(id(M*O),20n)
.extract tran min(i(X*.M*.d),20n)
.extract tran yval(v(x*.ti*),20n)
```

Quantities which allow wildcards are the same as those that can be used in . Probe, see ".PROBE" on page 838. The -R flag can be specified with wildcards so that all internal and external nodes of subcircuits beginning with the string specified will be probed, see description of . Probe -R in "Using Wildcards in Subcircuit Instances" on page 843.

The .extract command cannot be used on digital signals.

By default, extraction results are saved inside the $E X T$ folder in the main $w d b$ file which can be read by EZwave. Use option extrile to create a .ext. wdb file with the extraction results. The .ext. $w d b$ file will not always be created as it depends on the type of simulation and the specification of the .EXTRACT command.

## Backward compatibility

If using the .cou format, the .extract command also creates a .ext file when option extrile is specified in the netlist, depending on the type of simulation and the command specification.

When extraction statements are combined with parameter sweeping statements (.STEP), Eldo automatically creates waveforms showing the extraction results versus the swept parameter. If using the .cou format, these .EXTRACT waveforms are created in a separate file with the .ext extension. The command-line switch -couext (eldo -couext -i <netlist.cir>) can be used to merge the extract waveforms into the .cou file, when possible. In this case, a single .cou file will contain the raw waveforms and also the extraction waveforms.

## Related options

$" \operatorname{AEX}[=0|1| 2] "$ on page 1010
"AUTOSTOP=0 $11 \mid 2 "$ on page 974
"COMPEXUP" on page 951
"DUMP_EXTRACT=0|1" on page 999
"ENGNOT" on page 995
"EXTERR" on page 952
"EXTMKSA" on page 1000
"NODEFRMSNTR" on page 1004
"NUMDGT=INTEGER_VAL" on page 996

```
"ALIGNEXT" on page 1011
"AUTOSTOPMODULO=VAL" on page 975
"DEFRMSNTR" on page }99
"DUMP_MCINFO" on page 999
"EXTCGS" on page 1000
"EXTFILE" on page 1000
"EXTRACT_VECT_AXIS=INDEX|XAXIS"
on page 1001
"NOEXTRACTCOMPLEX" on page 1004
```


## Parameters

To ensure that compatibility with previous versions of Eldo is maintained, it is preferable to select one of the optional parameters from the following list:

## - EXTRACT_INFO

should be replaced with one of the following parameters;
AC
Extraction during AC analysis.
DC
Extraction during DC analysis.

DCTRAN
Extraction after the DC analysis performed prior to a TRAN analysis.
DCAC
Extraction after the DC analysis performed prior to an AC analysis.
DCSWEEP
DCSWEEP extraction.
TRAN
Extraction during TRAN analysis.
NOISETRAN $\mid$ NTR
Extraction during NOISETRAN analysis, see ".NOISETRAN" on page 747.
FOUR
Extract values from an FFT waveform.
DSP
Extract values from a DSP waveform, see ".DSP" on page 615.

## SWEEP

Used in conjunction with . STEP to extract values from a curve (EXTRACT $=$ FUNCTION (SWEEP_parameter)). It is also possible to specify the reference variable of a sweep. This reference variable can be a parameter or TEMP in the case of a .TEMP command.

```
SSTAC|SSTXF|SSTNOISE|SSTJITTER|TMODSST|FMODSST|FOURMODSST|TSST|
    FSST|SSTSTABIL
```

Please refer to the Display Command Syntax chapter of the Eldo RF User's Manual for more information regarding these RF options.

OPT
Extraction during optimization analysis. Can only be used with wave type wорт. This wave type is used for optimization analysis only, that is, it may only be used with орт. For more information on wave type wort, see "WOPT" on page 1191.

- LABEL=NAME

Label name of the extraction result. This can also be a string as shown below:

```
.EXTRACT [EXTRACT_INFO] [LABEL=NAME] <expression>
.EXTRACT [EXTRACT_INFO] [LABEL=" string "] <expression>
```

If a LABEL is specified, then you will obtain " LABEL "=result inside the output file and not <expression>=results.

- FILE=FNAME

Results will be dumped into the specified file. The values are also still written into the .chi file, that is, the same values and information are dumped in both files.

- UNIT=UNAME

Defines the unit of the extract. It is used when plotting the extract wave during a sweep analysis. This could be useful when you want to compare an extracted wave to a reference because by default EZwave displays separate axis.

## - VECT

Extract vectors. By default, . extract returns the first value which matches the expression. If keyword vect is set on the .extract statement, then all values will be returned. A waveform will be plotted in the EXT folder for extracts of type vector. This waveform will represent the value of the extract versus the index of the value.
Specific values already extracted using the .extract vect command can be used in a different .extract command. This is possible by identifying elements of a measurement specified with the vect keyword with [index]. For example:

```
v1 1 0 pulse ( 0 5 0 1n 1n 10n 50n)
r1 1 0 1
v2 2 0 pwl ( 0 0 100n 10)
r2 2 0 1
.extract tran vect label = tito yval(v(2),xthres(v(1),2.5))
.extract tran meas(tito[2])
.tran 1n 100n
```

The first extraction will create a vector of five elements. The second extraction will extract item number 2 of the first extract.

## Note

Note
Extraction with vECT does not work when it is done in reverse. In the instance below,
. EXTRACT VECT xup (v(1), 2.5, END, START)
the following message will be returned:
VECT keyword cannot be used when extracting backwards

## - CATVECT

Works in the same way as vect but in addition all measurements corresponding to all analyses (. STEP/. TEMP) will be combined. This functionality is usually used in conjunction with the contour function in the .plot command. For more information on the contour function, see "CONTOUR" on page 798.

- OPTIMIZER_INFO

Represents additional arguments for optimization. Note that these additional arguments (for example GOAL, Lbound) have no effect when the . OPtimize command is not specified in the netlist. For more information, please refer to ".EXTRACT and .MEAS" on page 1131.

- MC_INFO

Represents additional arguments for Monte Carlo analysis, including:
Table 10-10. Monte Carlo Extract Outputs

| LBOUND | UBOUND | MCMIN | MCAVG | MCSTD | MCVAR |
| :--- | :--- | :--- | :--- | :--- | :--- |
| MCSKEW | MCKURT | MCMOM | ICARLO | NBCARLO |  |

For more information, please refer to "Monte Carlo Output" on page 1215.

- INTERP_MODE

Specifies the interpolation mode. Only applies to the $y v a l()$ function. Given three simulation points: $\mathrm{P} 1(\mathrm{x} 1, \mathrm{y} 1), \mathrm{P} 2(\mathrm{x} 2, \mathrm{y} 2)$ and $\mathrm{P} 3(\mathrm{x} 3, \mathrm{y} 3)$; where $\mathrm{x} 1, \mathrm{x} 2$ and x 3 represent the simulation variable (time, frequency, ...); and $\mathrm{y} 1, \mathrm{y} 2, \mathrm{y} 3$ represent the value of a waveform for $\mathrm{x} 1, \mathrm{x} 2$ and x 3 respectively. Consider a search for value $\mathrm{y}=\mathrm{yval}$ (<waveform>,x) which represents simulation point $\mathrm{P}(\mathrm{x}, \mathrm{y})$, with P between P 2 and P 3 . interp_mode can take the following values:

LINEAR: means a linear interpolation is performed between P2 and P3 (default).
QUADRATIC: means a quadratic interpolation is performed between P1, P2 and P3.
SAMPHOLD: means the value is constant between two points and equal to the previous point, ( $\mathrm{y}=\mathrm{y} 2$ ).
histogram: means the value is equal to the previous point until the mid-point is reached, and is equal to next point after it:
if $(x<(x 2+x 3) / 2) y=y 2$;
else $y=y 3$;
SPECTRAL: means the value is 0 if the point has not been simulated precisely.

- tIME=value

Specifies a time for which an extract is active to extract information specific to one analysis. Only applies to AC and NOISE extracts when AC is performed during transient. For example:

```
.op 10n 30n 50n
.TRAN 1n 100n
.PLOT TRAN V(EP) V(S)
.AC DEC 10 1.OE3 1.0E9
.PLOT AC VDB(S)
.extract ac label=FOO1 yval(vdb(s),1g)
.extract ac label=FOO2 time=30n yval(vdb(s),1g)
.extract ac label=FOO3 yval(vdb(s),1g) time=50n
.extract ac label=FOO4 yval(vdb(s),1g) time=20n
```

For the extracts labelled FOO2 and FOO3, AC analysis information is extracted at the specified times. For the FOO4 extract, no extract is done, because no AC analysis is performed at 20 ns .

- \$MACRO

Instantiation of a macro previously defined using the .DEFMAC command. The macro name must be preceded by the $\$$ character.

- FUnCtion

Pre-defined function. The functions listed under "FUNCTION" on page 645 are available. Many of these functions use the optional parameters listed in the table below:

Table 10-11. Extract Function Parameters

| BEFORE=VAL | Causes the function to be performed only if TIME < val. |
| :--- | :--- |
| AFTER=VAL | Causes the function to be performed only if TIME > val. |
| OCCUR=VAL | Computes the function for the vALth occurrence of the event. |
| VTH=VAL | Voltage defining a threshold or starting point. |
| VTHIN=VAL | Voltage defining a threshold or starting point. |
| VTHOUT=VAL | Voltage defining a threshold or starting point. |
| VH=VAL | Voltage defining a threshold or starting point. |
| VL=VAL | Voltage defining a threshold or starting point. |
| WAVE | Valid waveform name or keyword xaxis. xAxIs extracts an x-axis <br> value when a condition becomes true, that is, refers to the TIME if <br> current simulation is transient, or frequency if current simulation is AC <br> analysis. You can use wildcards in wave names. |
| MIN | Minimum value on x-axis or keyword START. START corresponds to the <br> first value of the xAxIs, that is, the starting point of the simulation. |
| MAX | Maximum value on x-axis or keyword END. EnD refers to the last point <br> of the simulation. |

Functions can be used together with:

- Eldo operators such as the "Arithmetic Operators" on page 83 and "Boolean Operators" on page 83
- Output quantities (. .PRINT/. PLOT), such as those listed in the tables under "Plot Specifications (OVN)" on page 799
- Pre-defined functions as listed here under "FUNCTION" on page 645
- Extract accessor functions

Functions extract (), meas (), or initial_extract () can be used in .extract statements to perform an "extract of extract." This can be useful if you want to extract
the result of some extracts from a sweep analysis. If you want to use results of EXTRACT in another .EXTRACT command that applies to a single analysis, not to a sweep analysis, then specify the keyword AC, tran, or dCSWEEP, otherwise the value is not extracted. However, when there are no ambiguities, only one analysis being performed without . STEP or . TEMP commands, then the keyword is optional. A vector extract can also be used in an extract of extract, see extract of vector extract example.

EXTRACT (extract_label)
Extract accessor function used to access the value of a .EXTRACT, to perform an "extract of extract." For example:

```
.TEMP 10 20 30
.EXTRACT LABEL = T1 MAX(v(s))
.EXTRACT YVAL(EXTRACT(T1),20) ! extract T1 for T=20Celcius
```

Here, the second . ехтract is by default not evaluated after a single analysis, but only on completion of a SWEEP analysis; on completion of the three temperature analyses. See also a full extract of extract example.

MEAS (extract_label)
Alternative to the extract accessor function ехтract. Used to access the value of a .EXTRACT, to perform an "extract of extract."

INITIAL_EXTRACT (extract_label)
Extract accessor function used to access the value of a .EXTRACT inside subsequent . ALter statements. A syntax error is issued if this accessor is used in a netlist without .alter statements or if the .EXTRACT value is not available for the nominal netlist. Otherwise it is replaced by the .extract value. For example:

```
.paramopt p1=(4,1,10)
V1 1 0 pwl(0 0 5n 0 6n 'p1' 10n 'p1' 11n 0)
R1 1 0 1
.tran 1n 15n
.extract tran label=FOO max(v(1))
.alter
.optimize
.objective tran label=MM max(v(1)) goal='0.9*INITIAL_EXTRACT(FOO)'
.end
```


## Note

Transient extraction language functions and general purpose extraction language functions accept extract () and meas () keywords as parameters when they reference results from other . Ехtract commands. However, transient functions are implicitly converted to general purpose functions in this case, and the memory and speed advantage of transient functions is lost.

In all cases below where $V \mathbf{D D}$ and $\boldsymbol{V S S}$ are used in function definitions, $\boldsymbol{V D D}$ represents the larger, and VSS the smaller voltage input found in the netlist at $\boldsymbol{T I M E}=0$. These values are computed only once, even when a sweep is performed on VDD or VSS.

For all function arguments requiring a value, a parameter name may be passed to the function, the parameter value being specified via the following command:
.PARAM PARAM_NAME=VAL
For wave arguments used in the functions below, either the name of a waveform created using the .DEFWAVE command or a waveform expression may be used. For example:

```
.extract max(W('V(s)-V(a)'))
```

which is equivalent to:

```
.defwave my_wave=V(s)-V(a)
.extract max(W(my_wave))
```


## Two-port Noise Parameters

Any noisy two-ports can be represented by the equivalent noiseless two-port with the two equivalent noise sources ( $\boldsymbol{e}_{\mathrm{n}}$ and $\boldsymbol{i}_{\mathrm{n}}$ ) or the corresponding noise correlation matrix $\boldsymbol{C}^{\mathrm{A}}$. For more information on these parameters see "TWO_PORT_PARAM" on page 798.

It is also possible to use the center and radius of RF Gain/Noise circles in an extract command. The quantities are in the form:

```
<noise_circle>_R !(real part)
<noise_circle>_I !(imaginary part)
<noise_circle>_RAD !(radius)
```

where <noise_circle> can be any of the following: GAC, GPC, LSC, SSC, NC.

## FUNCTION

There are two types of Extraction Language:

- Transient Extraction Language:

Faster to execute, and consumes less memory. Transient extract language is based on the following functions:

Table 10-12. Transient Extraction Language Functions

| D_WA | DTC | SLEWRATE | TCROSS | TINTEG |
| :--- | :--- | :--- | :--- | :--- |
| TPD | TPDUU | TPDUD | TPDDU | TPDDD |
| TPERIOD | TRISE | TFALL | VALAT |  |

- General Purpose Extraction Language:

More expensive in terms of memory and CPU, but is much more general in the sense that arguments can be expressions. It is based on the following functions:

Table 10-13. General Extraction Language Functions

| AVERAGE | COMPRESS | CROSSING | DCM | DISTO |
| :--- | :--- | :--- | :--- | :--- |
| EVAL | FAIL | FALLING | INTEG | KFACTOR |
| LOCAL_MAX | LOCAL_MIN | MAXGMVT | MAX | MEAN |
| MIN | MODPAR | OPMODE | PASS | PVAL |
| RISING | RMS | SLOPE | VDSATC | VTC |
| WFREQ | WINTEG | XCOMPRESS | XDOWN | XMAX |
| XMIN | XTHRES | XUP | XYCOND | YVAL |

If MIN and MAX are not specified in a function call, information is returned when the CONDITION is true for the first time.

The x-axis values min and max may be replaced by the keywords Start and end to specify the beginning and end of the simulation interval respectively. The $x$-axis value MIN may be made greater than the MAX value. This causes Eldo to look backwards when CONDITION is true for the first time. This is useful for extracting waveform settling time data.

## AVERAGE

AVERAGE (WAVE [, MIN, MAX])
Returns the average value of the waveform WAVE in the x -axis range min to MAX. This is calculated as follows:

$$
A V E R A G E=\frac{1}{\max -\min } \times \int_{\min }^{\max } \text { waved } x
$$

## COMPRESS

COMPRESS (WAVE, VALUE [, SLOPE])
Extracts the Y-axis value of the wave at the point where the difference between the actual value of wave and the linear extrapolation of wave based on the computed slope value becomes greater than value.

SLOPE corresponds to the minimum slope which must be between the first two points of the wave. If the actual slope on the signal is not high enough, a message will be displayed.
Default for this third argument is 0.99 if the COMPRESS is performed on a SWEEP extract. Otherwise, it is undefined.

## CROSSING

```
CROSS[ING](WAVE, VALUE[, MIN, MAX[,OCCURENCE]])
```

Returns the x -axis value after the waveform wave has crossed occurence number of times the VALUE in the range min to MAX.

The crossing () function has two meanings when used inside xycond (), see "XYCOND" on page 660.

## D_WA

D_WA (WAVE1, WAVE2 [, AFTER=VAL])
Returns the distance between two waveforms. D_WA has the units of the waveforms, and is computed by dividing the area between the two waves by the x -axis range. D_WA may also be used in DCSWEEP to compare two characteristics of currents, for example:

```
.extract d_wa(v(a), v(b))
.extract d_wa(i(r1), id(m1))
```

DCM
DCM [(label_name)]
Returns the DC mismatch information for a specific label_name (see the .DCMISMATCH command). It extracts the value which is dumped in the .chi file, so you do not have to browse the .chi file to obtain that value. DCM can be specified without any argument (label_name) if there is no ambiguity about the name.

## DELTA

DELTA (OVN[, VGS=VAL] [,VDS=VAL] [, VBS=VAL])
Returns the difference between the value for the current run and the value calculated during the first run. Used with . STEP or . TEMP commands. ovn is any output quantity
(.PRINT/. PLOT). VGS, vDS and vbs define the pin voltages used for device evaluation, and are required when device-related outputs are used, for example: IDS(M1), GM(X1.M2), $\mathrm{VT}(*)$. In the following example, Eldo computes the delta IDSAT quantities between the current run and the first run:

```
.extract label=delta_ids delta(IDS(*), VGS=3, VDS=3, VBS=0)
```

The delta function can also be used with reliability analysis to return the difference between aged and fresh values. See Delta Extract Results in the Eldo UDRM User's Manual.

## DTC

DTC (WAVE [, VTH=VAL] [, AFTER=VAL] [, BEFORE=VAL])

Returns the duty-cycle of the waveform wave in transient analysis.
The duty cycle of the periodic waveform is the ratio of the "high" portion of the waveform to the length of the period.

The DTC extract is equivalent to the following three extracts if the first threshold is a rise time:

```
.extract tran label=period abs(xup(wave,vth,2) - xup(wave,vth,1))
.extract tran label=cycle abs(xdown(wave,vth,1) - xup(wave,vth,1))
.extract label=duty_cycle {extract(cycle)/extract(period)}
```


## DISTO

DISTO (WAVE, FUND_FREQ, FMIN, FMAX)
Returns the total harmonic distortion of a signal. FUND_FREQ is the fundamental frequency and FMIN and FMAX specify the window in which you require the harmonic distortion to be calculated.

The harmonics inside the interval [FMIN, FMAX] are then computed as follows:

$$
\text { harmonic }(i)=\left|\frac{A(i)}{A 0}\right|
$$

where:
$\boldsymbol{A}(\boldsymbol{i})=$ amplitudes of the multiples of the fundamental frequency
$\boldsymbol{A 0}=$ amplitude of the fundamental frequency
The Total Harmonic Distortion is given by the following:

$$
\text { tot_harm }=\sqrt{\sum \text { harmonic }(i)^{2}}
$$

where the sum is computed over all multiples $(\geq 2)$ of the fundamental frequency in the specified band. If these values are not identical to the sampled data values, then they are computed by interpolation.
The results of the harmonic distortion are given as a percentage ( $100 \times$ tot_harm).

```
.extract four disto(fourdb(fft_label),5meg,0,2.5e8)
.extract fsst disto(vm(node),75meg,10meg,600meg)
```


## EVAL

```
\(\mathbf{E}[\) VAL ] (INSTANCE, \(\mathbf{W}|\mathbf{I}| \mathbf{A D}|\mathbf{A S}| \mathbf{P D}|\mathbf{P S}|\) AREA)
E[VAL] (INSTANCE, Weff|Leff ADeff|ASeff|PDeff|PSeff|Geo|RDeff|RSeff)
E[VAL] (dipole_name)
```

Returns the value of the requested parameter for the circuit element InSTANCE or the dipole_name. The instance must be declared before the .EXTRACT command. For example:

```
extract eval(m1, w)
```

The second syntax shows additional parameters which are only available for MOSFETs.
Specify option extract_eval_final for eval (device_name, device_entity) to take into account the scale factor, option sCALE, if specified. See "EXTRACT_EVAL_FINAL" on page 1000 .

## FAIL

FAIL (label)
Provides information on whether an extraction passed or failed. Returns 1.0 if extract <label> was not successfully measured and 0.0 otherwise. label is the label name of the extraction result as specified in a previous extract statement. For example:

```
.extract tran label=UP500MV xup(v(IN),2.5)
.extract tran label=EX1 FAIL (UP500MV)
```


## FALLING

FALLING (WAVE, VALUE[, MIN, MAX[,OCCURENCE]])
Returns the x -axis value after the waveform WAVE has fallen OCCURENCE number of times below Value in the range min to max.

The falling () function has two meanings when used inside xycond (), see "XYCOND" on page 660.

## INTEG

INTEG (WAVE [, MIN, MAX])
Returns the integral of the waveform WAVE in the x-axis range min to max. This is calculated as follows:

$$
\text { INTEG }=\int_{\min }^{\max } \text { wavedx }
$$

## KFACTOR

Computes the stability factor for 2-ports. The keyword returns:

$$
\frac{\left(1.0-|S 11|^{2}-\left(|S 22|^{2}+|S 11 \times S 22-S 12 \times S 21|^{2}\right)\right)}{(2 \times|S 12 \times S 21|)}
$$

S11, S22, and so on, are the S parameters. This is available with AC and FSST results.
LOCAL_MAX
LOCAL_MAX (WAVE [, MIN, MAX])
Used without the vect keyword, returns the first local maximum value of the waveform WAVE in the x -axis range MIN to MAX.
Used with the vect keyword, returns all the local maxima of the waveform WAVE in the x-axis range min to MAX, and if option extract_vect_axis=xaxis is set (see
"EXTRACT_VECT_AXIS=INDEX|XAXIS" on page 1001) the resulting waveform matches the EZwave Local Max measurement, see Local Max in the EZwave User's and Reference Manual.

## LOCAL_MIN

```
LOCAL_MIN(WAVE [, MIN, MAX])
```

Used without the vect keyword, returns the first local minimum value of the waveform WAVE in the x -axis range min to MAx.

Used with the vect keyword, returns all the local minima of the waveform wave in the x-axis range min to max, and if option extract_vect_axis=xaxis is set (see "EXTRACT_VECT_AXIS=INDEX|XAXIS" on page 1001) the resulting waveform matches the EZwave Local Min measurement, see Local Min in the EZwave User's and Reference Manual.

## MAXGMVT

MAXGMVT (Mxx [, VDS, VGSMIN, VGSMAX])
Returns the maximum transconductance threshold voltage for the MOS with instance name Mxx . The value is computed by sweeping the voltage across the gate and source of the MOS across a range defined by vgSmin (minimum gate source voltage) and vgSmax (maximum gate source voltage), and is the x -intercept of the maximum slope tangent line to an Id-Vg curve at a fixed Vds-Vds/2.


If vds (drain source voltage), vgSmin and vgSmax are not specified then the following default values are internally calculated and used:

```
VDS = 0.1
VGSMIN = LV9(Mxx) - 0.5
VGSMAX = LV9(Mxx) + 0.5
```

Example using default values:

```
.extract dc label = MAX_GM_VT1 maxgmvt(m01)
```

Example when specifying the values:

```
.extract dc label = MAX_GM_VT2 MAXGMVT(M1, 0.1, 0, 2.0)
```


## MAX

MAX (WAVE [, MIN, MAX])
Returns the maximum value of the waveform WAVE in the x -axis range MIN to MAX.

## MEAN

MEAN (WAVE [, MIN, MAX])
Returns the mean value of the waveform WAVE in the $x$-axis range MIn to MAX. This is calculated as the sum of waveform values in [MIN, MAX] divided by the number of points between [min, mAx].

## MIN

MIN (WAVE [, MIN, MAX])
Returns the minimum value of the waveform WAVE in the $x$-axis range MIN to MAX.

## MODPAR

```
MODPAR(MODNAME, PARAM_NAME)
```

Returns the value of the parameter, PARAM_NAME, of the model, MODNAME.
To extract the value of a parameter of a model defined inside a subcircuit:

- When no model parameters are an expression of an instance parameter, to extract a model parameter defined inside a subcircuit use the syntax modpar(subckt_name.model_name, parameter_name), for example:

```
.extract dc modpar(toto.tutu, vt0)
```

- When some model parameters are an expression of an instance parameter, to reach a model parameter defined inside a subcircuit use the syntax modpar(hierarchical_instance_name.model_name, parameter_name), for example:

```
.extract dc modpar(x1.tutu, vt0)
```


## OPMODE

OPMODE (DEVICE_NAME)
Returns the DC working mode of the device model, DEVICE_NAME.
Eldo extracts the DC working mode of a device as a string instead of a real value. Strings returned are:

- for MOS devices:

LINEAR, if $V G S>V T$ and $V D S<V D S A T$
saturation, if $V G S>V T$ and $V D S>V D S A T$
subthreshold, if $V G S<V T$

- for BJT devices:
saturation, if $V B E>0$ and $V B C>0$
on, if $V B E>0$ and $V B C<0$
OFF, if $V B E<0$ and $V B C<0$
inverse, if $V B E<0$ and $V B C>0$
PASS
PASS (label)
Provides information on whether an extraction passed or failed. Returns 1.0 if extract label was successfully measured and 0.0 otherwise. label is the label name of the extraction result as specified in a previous extract statement. For example:

```
.extract tran label=UP500MV xup(v(IN),2.5)
.extract tran label=EX2 PASS (UP500MV)
```


## PVAL

PVAL (parameter_name)
Returns the value of the requested parameter.

## RISING

RISING (WAVE, VALUE[, MIN, MAX[,OCCURENCE]])
Returns the x -axis value after the waveform WAVE has risen OCCURENCE number of times above VALUE in the range MIN to MAX.
The rising () function has two meanings when used inside xycond (), see "XYCOND" on page 660 .

## RMS

RMS (WAVE [, MIN, MAX])
Returns the root mean square value of the waveform WAVE in the x -axis range MIN to MAX.
This is calculated as follows:
$R M S=\sqrt{\left(\left[\int_{\min }^{\max } \text { wave }^{2}\right] d x /(\text { max }- \text { min })\right)}$ for transient analysis and for Eldo RF time domain signals (TRAN, TSST)
$R M S=\sqrt{\left(\int_{\min }^{\max } \text { wave }^{2}\right)}$ for AC analysis and for Eldo RF frequency domain signals (AC, SST, NOISE, SSTNOISE, and so on)

For noise analysis, RMS calculations can not be performed in the same way as for other analyses, because of the specific nature of noise signals. RMS for noise analysis can be achieved with the following syntax:

```
.extract RMS(inoise)
.extract RMS (onoise)
.extract RMS (noise(Q1))
```

RMS (inoise) is calculated as:

$$
R M S(\text { inoise })=\sqrt{I N T E G(I N O I S E \times I N O I S E)})
$$

RMS (onoise) is calculated as:
$R M S($ onoise $)=\sqrt{I N T E G(\text { ONOISE } \times \text { ONOISE })})$
RMS (noise (object)) is calculated as:
$\operatorname{RMS}($ noise $($ object $))=\sqrt{\operatorname{INTEG(NOISE}(\text { OBJECT }))}$

## SLEWRATE

```
SLEWRATE (WAVE [, VTH=VAL [, BEFORE=VAL] [, AFTER=VAL] [, OCCUR=VAL])
```

See the descriptions of these parameters under "FUNCTION" on page 643.
Returns the slope of the waveform WAVE at $v($ wave $)=v t h$. Default is $v t h=\frac{(V D D+V S S)}{2}$

## SLOPE

SLOPE (WAVE, VTH [, MIN, MAX] [, n])
Returns the slope of the waveform WAVE at the nth occurrence of it crossing the $y$-axis value vth in the x -axis range min to MAX.

## TCROSS

TCROSS (WAVE [, VTH=VAL] [, OCCUR=VAL] [, AFTER=VAL] [, BEFORE=VAL])
Equivalent to the xthres function. тcross is part of the 'Transient-extraction language', while xthres is part of the 'general-purpose extraction language'. The former mode is faster to execute, and consumes less memory, while the latter is more expensive in terms of memory and CPU, but is much more general in the sense that arguments can be expressions. The default value of $\mathbf{v т н}$ is calculated using the values of the voltage sources in the design. $V T H=v \min +0.1 \times(v \max -v \min )$; where vmin is the lowest source value in the design and vmax is the highest value.

## TINTEG

```
TINTEG(WAVE, [AFTER=VAL] [, BEFORE=VAL])
```

Equivalent to the integ function. tinteg is part of the 'Transient-extraction language', while INTEG is part of the 'general-purpose extraction language'. The former mode is faster to execute, and consumes less memory, while the latter is more expensive in terms of memory and CPU, but is much more general in the sense that arguments can be expressions.

## TPD

```
TPD (WAVE1, WAVE2 [, VTH=VAL] [, VTHIN=VAL] [, VTHOUT=VAL]
+ [, BEFORE=VAL] [, AFTER=VAL] [, OCCUR=VAL])
```

See the descriptions of these parameters under "FUNCTION" on page 643.
Returns the propagation delay between wavel and wave 2 . The thresholds vthin and vthout are defined for WAVE1 and Wave2 respectively.
vinin is the threshold voltage to be used to detect transition on the first node given in the TPD command (for example TPD (V(IN), V (OUT))), while VTноит is the threshold voltage for the second node (V (out) in this example). If vthin equals vthout, it is possible to specify only vтн.
Default is $v t h=\frac{(V D D+V S S)}{2}$.

If there is more than one transition, the average of the first and second is used. To measure specific signal transitions (for example, rising/falling on the input/output), the following functions may be used: TPDUU, TPDUD, TPDDU, and TPDDD.
If occur=val is specified, Eldo returns the $\operatorname{TPD}$ at the val ${ }^{\text {th }}$ occurrence of the threshold crossing. The default value of OCCUR is 1 . OCCUR=1 means Eldo returns the TPD value for the first occurrence of the threshold crossing, occur=2 for the second occurrence, and so on. OCCUR=1 is between the first edge of WAVE1 and the next edge of WAVE2. OCCUR=2 is between the next edges of WAVE1 and WAVE2.
Alternatively, you can use AFTER=val and beFore=val in order to tell Eldo to return trd values only if both threshold are crossed in the specified time interval.

## TPD Examples

Assume $\mathrm{V}(\mathrm{In})$ crosses vthin at 10 n 50 n and 100 n , assume V (OUT) crosses vthout at 5 n 75 n and 110 n :

TPD (V (IN) , V (OUT) , OCCUR=1)
would return $65 \mathrm{n}(75 \mathrm{n}-10 \mathrm{n})$, while:
TPD (V (IN) , V (OUT) , OCCUR=2)
would return 10n (110n-100n) (second occurrence).
However, $\operatorname{TPD}(V(I N), V(O U T))$ would return 37.5 n (average between the first $\operatorname{TPD}$ in one direction and the first TPD in the other direction).

Figure 10-4 illustrates this simple example of trd.
Figure 10-4. TPD Example


## TPDUU

```
TPDUU(WAVE1, WAVE2 [, VTH=VAL] [, VTHIN=VAL] [, VTHOUT=VAL]
+ [, BEFORE=VAL] [, AFTER=VAL] [, OCCUR=VAL])
```

WAVE1 and WAVE2 are both rising. For example:

```
.extract tran tpduu(v(in),v(out),vth=2.5,occur=3)
```

Eldo returns the propagation delay between $v(i n)$ and $v$ (out) for the third occurrence of both waveforms rising above the 2.5 V threshold.

## TPDUD

TPDUD ((WAVE1, WAVE2 [, VTH=VAL] [, VTHIN=VAL] [, VTHOUT=VAL]

+ [, BEFORE=VAL] [, AFTER=VAL] [, OCCUR=VAL])
WAVE1 is rising, WAVE2 is falling. For example:

```
.extract tran tpdud(v(in),v(out),vth=2.5,occur=3)
```

Eldo returns the propagation delay between $v(i n)$ and $v$ (out) for the third occurrence of waveform $\mathrm{v}(\mathrm{in})$ rising above the 2.5 V threshold and waveform v (out) falling below the same threshold.

## TPDDU

```
TPDDU(WAVE1, WAVE2 [, VTH=VAL] [, VTHIN=VAL] [, VTHOUT=VAL]
+ [, BEFORE=VAL] [, AFTER=VAL] [, OCCUR=VAL])
```

WAVE1 is falling and WAVE2 is rising. For example:

```
.extract tran tpddu(v(in),v(out),vth=2.5,occur=3)
```

Eldo returns the propagation delay between $v(i n)$ and $v($ out ) for the third occurrence of waveform $\mathrm{v}(\mathrm{in})$ falling below the 2.5 V threshold and waveform v (out) rising above the same threshold.

## TPDDD

```
TPDDD(WAVE1, WAVE2 [, VTH=VAL] [, VTHIN=VAL] [, VTHOUT=VAL]
+ [, BEFORE=VAL] [, AFTER=VAL] [, OCCUR=VAL])
```

WAVE1 is falling and WAVE 2 is falling. For example:

```
.extract tran tpddd(v(in),v(out),vth=2.5,occur=3)
```

Eldo returns the propagation delay between $v(i n)$ and $v$ (out) for the third occurrence of both waveforms falling below the 2.5 V threshold.

## TPERIOD

TPERIOD (WAVE [, VTH=VAL] [AFTER=VAL] [, BEFORE=VAL])
Returns the $x$-axis interval corresponding to the crossing of a $y$-axis value VTH by waveform WAVE in the $x$-axis range [AFTER, BEFORE]. The first crossing determines if the x -axis interval is measured between rising edges or falling edges.

The default value of VTH is calculated using the DC values of the voltage sources in the design. $\mathrm{VTH}=\mathrm{vmin}+0.1 \times(\mathrm{vmax}-\mathrm{vmin})$ where vmin is the lowest source value in the design and vmax is the highest value.

## TRISE

TRISE (WAVE [, VH=VAL] [, VL=VAL] [, BEFORE=VAL] [, AFTER=VAL]

+ [, OCCUR=VAL])
Returns the rise time of the next rising edge on WAVE.


## TFALL

TFALL (WAVE [, VH=VAL] [, VL=VAL] [, BEFORE=VAL] [, AFTER=VAL]

+ [, OCCUR=VAL])
Returns the fall time of the next falling edge on WAVE.
See the descriptions of these parameters under "FUNCTION" on page 643. vh and vL are the high and low voltages defining the start and end points of the rise/fall. Defaults are:

$$
\begin{aligned}
& v l=V S S+0.1 \times(V D D-V S S) \\
& v h=V S S+0.9 \times(V D D-V S S)
\end{aligned}
$$

## VALAT

VALAT (WAVE, AT=VAL)
Returns the value of the waveform WAVE extracted at time VAL, for example:

```
.EXTRACT VALAT(v(s),AT=10n)
```

Returns the value of $\mathrm{v}(\mathrm{s})$ extracted at time 10 ns .

## VDSATC

VDSATC (Mxx [, IDS_NORM, VDS, VGSMIN, VGSMAX])
Returns the threshold voltage for the MOS with instance name Mxx. The value is computed by sweeping the voltage across the gate and source of the MOS across a range defined by VGSMIN and VGSMAX and is the VDSS for which the normalized drain source current IDS_NORM ( $\mathrm{Id} \times \mathrm{L} / \mathrm{W}$ ) is equal to a given value at a fixed Vds.
If IDS_NORM, VDS, VGSMIN and VGSMAX are not specified then the following default values are internally calculated and used:

$$
\begin{aligned}
& \text { IDS_NORM = 600n } \\
& \text { VDS }=0.1
\end{aligned}
$$

$$
\begin{aligned}
& \text { VGSMIN }=\operatorname{LV} 9(\mathrm{Mxx})-0.5 \\
& \text { VGSMAX }=\mathrm{LV} 9(\mathrm{Mxx})+0.5
\end{aligned}
$$

Example using default values:

```
.extract dc label = VDSATC1 VDSATC (m01)
```

Example when specifying the values:

```
.extract dc label = VDSATC2 VDSATC(M1, 600e-9, 0.1, 0, 2.0)
```

VTC
VTC (Mxx [, IDS_NORM, VDS, VGSMIN, VGSMAX])
Returns the threshold voltage for the MOS with instance name Mxx. The value is computed by sweeping the voltage across the gate and source of the MOS across a range defined by VGSMIN and VGSMAX and is the threshold voltage (VT) for which the normalized drain source current IDS_NORM (Id $\times \mathrm{L} / \mathrm{W}$ ) is equal to a given value at a fixed Vds.

If IDS_NORM, VDS, VGSMIN and VGSMAX are not specified then the following default values are internally calculated and used: IDS_NORM $=600 \mathrm{n}, \mathrm{VDS}=0.1, \mathrm{VGSMIN}=$ LV9(Mxx) - 0.5, VGSMAX $=\mathrm{LV} 9(\mathrm{Mxx})+0.5$.
Example using default values:

```
.extract dc label = VTC1 VTC(m01)
```

Example when specifying the values:

```
.extract dc label = VTC2 VTC(M1, 600e-9, 0.1, 0, 2.0)
```


## WFREQ

WFREQ (WAVE [, START, END])
Returns the average frequency of the waveform WAVE between the times START and END, for example:

```
.EXTRACT WFREQ(V (OUTPUT), 10n, 100n)
```

Returns the average frequency of the voltage on node output between 10 n and 100 n .

## WINTEG

```
WINTEG(WAVE [, T]
```

Returns the time integral of the waveform wave from 0 to T . This is calculated as follows:

$$
W \operatorname{INTEG}=\int_{0}^{t} w \operatorname{wave}(u) d u
$$

When winteg is used in .Defwave cards, the corresponding waves are dumped in .meas rather than in the binary output file.

## XCOMPRESS

XCOMPRESS (WAVE, VALUE [, SLOPE])
Extracts the X -axis value of the wave at the point where the difference between the actual value of wave and the linear extrapolation of wave based on the computed slope value becomes greater than value.
SLOPE corresponds to the minimum slope which must be between the first two points of the wave. If the actual slope on the signal is not high enough, a message will be displayed.
Default for this 3rd argument is 0.99 if the xCOMPRESS is performed on a SWEEP extract. Otherwise, it is undefined.

Using the compress/xcompress function is especially useful in the case of parametrized simulations (. STEP). It works in the following way:

- compute the slope of wave on the first two points
- when the difference between the actual value of wave and the linear extrapolation of wave based on the slope value computed at step 1 becomes greater than value, then Eldo will return the value of the wave at that point (compress function), or the X -axis value at which the difference occurs (xcompress function).

See also COMPRESS and for further information see ".EXTRACT—Compression Point Values" on page 665.

## XDOWN

XDOWN (WAVE, VTH [, MIN, MAX] [, n])
Returns the $x$-axis value of the waveform WAVE at the nth occurrence of it falling below a $y$-axis value vth in the $x$-axis range min to MAX.

## XMAX

XMAX (WAVE [, MIN, MAX])
Returns the value of the $x$-axis when MAX value is reached, for example:

```
.EXTRACT TRAN XMAX (v (out))
```

Returns the time at which v (out) reaches its maximum value.

## XMIN

XMIN (WAVE [, MIN, MAX])
Returns the value of the x -axis when MIN value is reached.

## XTHRES

Xthres (WAVE, VTH [, MIN, MAX] [, n])
Returns the x -axis value of the waveform WAVE at the nth occurrence of it crossing a y -axis value Vth in the x -axis range min to MAX.

## XUP

XUP (WAVE, VTH [, MIN, MAX] [, n])
Returns the x -axis value of the waveform WAVE at the nth occurrence of it rising above a $y$-axis value vth in the $x$-axis range min to mAx, for example:

```
.EXTRACT XUP(V(S),2.5,100n,300n,5)
```

Returns the $x$-axis value when $v(S)$ rises above 2.5 on the $y$-axis for the 5th time between 100 n and 300 n .

## Note

For slope, xdown, xthres, and xup functions: occurrence is always assumed to be 1 if the search occurs in the reverse direction, for example:
XUP (V(s) , 2.5, end, start)
XUP (V (s) , 2.5, end, start, 5)
Both will return the last $x$-axis value when $\mathrm{V}(\mathrm{S})$ crosses above 2.5 on the $y$-axis.

## XYCOND

```
XYCOND (WAVE, CONDITION [, MIN, MAX])
```

XYCOND (WAVE, WAVE2=vth)

Returns the value of the waveform WAVE when the expression represented by CONDITION is true for the first time, evaluated between the limits MIn to MAX. Parameter wAVE may be a valid waveform name or the keyword XAXIS which extracts an x -axis value when a condition becomes true. The parameter CONDITION may contain any of the available arithmetic expressions.

Table 10-14. XYCOND Arithmetic Expressions

| $==$ | Equal |
| :--- | :--- |
| $!=$ | Not equal |
| $\\|$ | Or |
| $\& \&$ | And |
| $<$ | Less than |
| $>$ | Greater than |

The rising (), falling(), and crossing () functions have two meanings when used inside XYCOND (). Specified inside the condition argument, they are boolean functions which return 1 if the signal crossed the threshold, and 0 otherwise. Specified inside the start and end arguments (MIN, MAX), they are equivalent to XUP (), XDOWN(), and XTHRES() respectively.

## YVAL

YVAL (WAVE, X_VALUE)
Returns the $y$-axis value of waveform WAVE when an $x$-axis value x_VALUE is reached. Complex results information instead of real values are enabled by default. For example, .extract ac label=EX1 yval(v(out),10k) would deliver the result:

* EX1 = 10.011 , -1.8

The general form is: real_part, imaginary_part.
Setting option noextractcomplex (see "noextractcomplex" on page 1004) disables this complex result information.
Keyword INTERP_MODE can be used to specify the interpolation mode. It applies only to the yval() function.

When the vector mode extract is specified (keyword VECT) then the x -axis value is automatically incremented even when explicitly specified. For example:

```
.extract ... vect yval(v(a), 10n)
```

generates the $v(a)$ value at every 10 ns interval.

## Examples

This example extracts the time when the voltage on node 1 rises to a value of 2.5 V between the range 0 and 100 ns and lists the results to the .chi file:

```
.extract xup(v(1), 2.5, 0, 100n)
```

The example below extracts the maximum value of the user defined waveform power_vdd and lists the results to the ASCII output file:

```
.extract max(w(power_vdd))
```

The example below extracts the average value of the power waveform of voltage source v1 (equivalent to .conso command) and lists the results to the ASCII output file:

```
.extract tran average(pow(V1))
```

The example below extracts the value of the power waveform of voltage source v 1 at $\mathrm{T}=0$ and lists the results to the ASCII output file:

```
.extract tran pow(V1)
```

The example below extracts the first occurrence of the phase of the voltage on node $s$ when the magnitude of the voltage on node $s$ is less than 0 dB in the range of the simulation interval and lists the results to the ASCII output file:

```
.extract xycond(vp(s), vdb(s)<0.0, start, end)
```

The next, more complex, example extracts the delay between the voltages on nodes 1 and 2 of the circuit and lists the results in the .chi file:

```
.extract xup(v(1), 2.5, 0, 100n) -
+ xdown(v(2), 2.5, 0, 100n)
```

The example below defines a macro called phmag with arguments a and b . This macro is then instantiated via the .extract command with the arguments a and $b$ being replaced by the phase voltage $\mathrm{vp}(\mathrm{s})$ and magnitude $\mathrm{vdb}(\mathrm{s})$ on node s respectively. The results are listed in the ASCII output file. The phmag macro uses the pre-defined functions xycond and yval:

```
.defmac phmag(a, b) = xycond(a, b<0.0) - yval (a, 0.001)
.extract $phmag(vp(s), vdb(s))
```

The example below extracts the value of waveform $v(1)$ when waveform $v(2)$ reaches 3 for the first time.

```
.extract tran xycond(v(1),v(2)==3)
```

It is also possible to extract values from a FFT waveform. Eldo will print out the value (in dB ) at 5 Meg for the FFT done on $v(A)$ :

```
.FOUR LABEL = t1 V(a)
.EXTRACT FOUR YVAL (FOURDB(t1),5MEG)
```

In the example below, 10 simulations will be made with P1 varying from 1 to 10 . There will be an extracted value for each of the 10 values of P 1 . The .ext file contains the information
$\boldsymbol{E X T R A C T E D} \_V A L U E S=\boldsymbol{f}($ stepped_value $)$; this file can be read by EZwave:

```
.STEP P1 1 10 1
.EXTRACT MIN(V(OUT))
```

In this next example, eleven analyses are performed for P1 varying from 1p to 10p. After each analysis, $\operatorname{MAX}(\operatorname{VDB}(S))$ is extracted; at that step, the second .EXTRACT command is ignored. Once the 11 simulations are complete, Eldo will interpret the .extract sweep... commands, and will then extract toto, that is, $\operatorname{MAX}(\operatorname{VDB}(\mathrm{S}))$ when P 1 was 5 p :

```
.PARAM p1 = ..
C1 S O p1
.STEP PARAM P1 1p 10p 1p
.EXTRACT LABEL=toto MAX(VDB(S))
.EXTRACT SWEEP YVAL (MEAS (toto), 5p)
```

The next example shows how to use the results of EXTRACT in another .Extract command that applies to a single analysis, with the keyword tran specified. When there are no
ambiguities, that is, only one analysis being performed, without .STEP or .TEMP commands, then the keyword is optional:

```
.TRAN 1n 10n
.TEMP 10 20 30
.EXTRACT LABEL = T1 MAX(v(s))
.EXTRACT LABEL = T2 MIN(v(a))
.EXTRACT TRAN EXTRACT(T1)-EXTRACT(T2) ! keyword TRAN expected
```

The following is an example of the results of an .EXTRACT command dumped into a specified file file.aex:

```
EXTRACT for AC ANALYSIS
    TEMPERATURE = 2.700000e+01 Celcius
        *YVAL (VDB (NET4),100K) = -1.01E+02
EXTRACT for TRANSIENT ANALYSIS
    TEMPERATURE = 2.700000e+01 Celcius
        *V(NET4) = 1.93E-09 Volts
        *YVAL(V(NET4),50N) = 1.40E+00
```

The following example shows how the vect keyword can be used to return all the values which match the expression. By default, .extract returns the first value which matches the expression.

```
v1 1 0 pulse(0 5 0 1n 1n 8n 20n)
r1 1 0 1
.extract vect xup(v(1),2.5)
.meas vect tran memes trig at 0 targ v(1) val=2.5 rise=1
.tran 1n 100n
.end
```

The following examples show how gain, phase margin, and gain margin can be extracted.

```
.EXTRACT label=gain max(W('v(output)/v(input)'))
.EXTRACT ac label=phmargin
+ {180 - yval(vp(VO),1m) + xycond(vp (VO),vdb (VO)<0)}
.EXTRACT ac label=gmargin
+ xycond(vdb(VO), 180+vp(VO) <yval(vp (VO),1m))
```

It is possible to specify the reference variable of a sweep in the sweep keyword. This reference variable can be a parameter or TEMP in the case of a .TEMP command. The example below shows two nested sweeps, and an extract. The . $w d b$ file will contain five waveforms for EXTRACT(T1) with the x -axis being the phase value and one waveform with the x -axis being FREQU value. A new waveform will be generated which is the value of the extract as a function of the second sweep parameter. An extract on this waveform is performed, then the value of the second extract as a function of the first swept parameter is obtained.

```
* nested sweep extract
.param frequ=1k phase=0
v1 1 0 sin (0.5 0.5 frequ 0 0 phase)
r1 1 0 1k
.tran 0 '2/frequ'
.step param frequ 0.8 1.2 INCR 0.1
.step param phase list -180 -90 0 90 180
.extract tran label=t1 xthres(v(1), 0.5) unit=Time ! versus Phase
```

. EXTRACT SWEEP (frequ) label=t2 max(meas(t1)) unit=Time ! versus Freq

You can access a single value of a vector extract. For example, if the following command line:

```
.EXTRACT tran vect label=fall xdown(v(ep),0.8)
```

generates the following output:

```
FALL[1] = 4.1200E-08
FALL[2] = 1.2120E-07
FALL[3] = 2.0120E-07
FALL[4] = 2.8120E-07
```

Then it is possible to use the second value in another EXTRACT expression using:

```
EXTRACT(FALL[2])
```

A full extract of extract example can be found in the software delivery tree:
\$MGC_AMS_HOME/examples/eldo/extract_of_extract.cir. The netlist is shown below:

```
* Extract Exercice
fns in out 1, 1 1e-7 8e-14
.param vhi=1
vin in O dc O ac 1 pulse O vhi 1u 1n 1n 5u 20u
*** AC Extraction ***
.tran 1u 10u
.plot tran v(in) v(out)
.probe tran v(out)
*** TRAN Extraction ***
.extract tran label=maxwave max(v(out))
.extract tran label=maxofmax max(extract(maxwave))
.option eps=1e-7
.step param vhi 5 1 1
.end
```

The extract labelled MAXWAVE is performed for each value of parameter VHI. EXTRACT(MAXWAVE) represents a waveform with VHI values for the $x$-axis and MAXWAVE values for the y-axis. Then the extract labelled MAXOFMAX is performed when all values of MAXWAVE are available: once the sweep is complete.

The following example shows another extract of extract scenario, where the first .EXTRACT returns a vector. For example, the statement below extracts the four time points at which v(clk) drops to 0.4 V :

```
.extract vect tran label=clk_fall xdown(v(clk), 0.4)
```

Then to extract the value of $v(T O P)$ at the four time points already calculated for clk_fall above, use:

```
.extract tran label=data_vals yval(v(top), meas(clk_fall[]))
```


## .EXTRACT—Compression Point Values

The compress/xcompress functions extract the co-ordinates of a compression point in the curve specified in the first parameter of the function. xcompress provides the X -value and compress the Y-value.

This compression point is the point where the curve is value below the straight line defined by the slope of the curve at the origin. (value is the second parameter of the function.)


In the illustration above, the curve is meas (POUTDBm), and the compression (value) is 1.0 dBm .

## Caution

When these functions are used to extract compression points, the swept parameter (Xaxis) and the curve ( Y -axis) must be in dB (or dBm ).

## Example

```
* 1dB compression point
.param fund=900Meg
.extract fsst label=POUTdBm YVAL(PdBm(RL), fund)
.extract sweep xcompress(meas(POUTdBm), 1.0)
.extract sweep compress(meas(POUTdBm), 1.0)
```


## .EXTRACT—Used with Monte Carlo Analysis

At the end of a Monte Carlo simulation, Eldo prints in the .chi file a histogram for each . extract command. The example below shows the .chi file entry for a Monte Carlo analysis with the following . Ехтtract command:

```
.EXTRACT tran label=tpd tpdud(v(in), v(out))
Distribution of TPD
    Range [ 9.8405E-10 1.7374E-09]
    Nominal value: 1.3124E-09
    Average value: 1.2709E-09
```



To produce a histogram such as the one shown above, a Monte Carlo analysis (. MC) with at least nine runs must be performed.

Note
The histogram is also output in the binary output file and can be displayed with EZwave.


For more information about Monte Carlo Analysis, see ".MC" on page 706 and the Monte Carlo Analysis chapter, and for output extraction see "Monte Carlo Output" on page 1215.

## .FFILE

## S, Y, Z Parameter Output File Specification <br> . FFILE $\mathbf{S}|\mathbf{Z}| \mathbf{Y}|\mathbf{G}| \mathbf{H}|\mathbf{T}| \mathbf{A} \quad$ [SINGLELINE] FILENAME [HZ $\mid$ KHZ $|\mathbf{M H Z}| \mathbf{G H Z}] \quad$ [RI $|\mathbf{M A}| \mathbf{D B}]$

1. For more information, see "Output File Specification" on page 1045 and "Touchstone Data Format" on page 1058.

## Parameters

- s

Specifies S (Scattering) frequency parameters tabulation.

- $\mathbf{Y}$

Specifies Y (Admittance) frequency parameters tabulation.

- $\mathbf{z}$

Specifies Z (Impedance) frequency parameters tabulation.

- G

Specifies G (Hybrid-G) matrix parameters tabulation.

- $\mathbf{H}$

Specifies H (Hybrid-H) matrix parameters tabulation.

- $T$

Specifies T (transfer scattering) matrix parameters tabulation.

- A

Specifies A (chain or ABCD) matrix parameters tabulation.

- filename

Name of the file where the S, Y or Z parameters will be stored.

- SINGLELINE

This enables the user to obtain the S-parameter file in single line format as shown below.

```
Freq S11 S21 S12 S22
```

- HZ

Specifies the units to be Hz . This is the default.

- KHz

Specifies the units to be kHz .

- MHZ

Specifies the units to be MHz.

- GHZ Specifies the units to be GHz.
- RI

Specifies Real Imaginary storage format. This is the default.

- MA

Specifies Magnitude Angle storage format.

- DB

MA with magnitude in dB.
Two-port noise parameters NFMIN_MAG, GAMMA_OPT_MAG, PHI_OPT and RNEQ are automatically written to the specified output file when a .NOISE command is specified in the netlist and the circuit to be analyzed is a two-port circuit.


## Examples

(1) For examples, see "Output File Specification" on page 1045.

## .FILTER

## Filter Data Driven Simulations

```
.FILTER AC|DC|TRAN|MODSST|SST|ALL [condition]
.FILTER EXTRACT [LABEL=label] [condition]
.FILTER DATA DATA_IN=input_data DATA_OUT=output_data [condition]
```

This command provides filtering capability for simulations, extractions, or to create subsets of .DATA statements. The filter is a logical expression, using the .PARAM syntax. Expressions can be entered directly or as a reference to a . PARAM. The filtering expression can involve the parameters used in a .DATA block in case of data driven simulations, usual parameters defined by .PARAM, and predefined keywords which identify an internal state, such as a Monte Carlo run index. If no condition is specified, all entries are taken into account.
$\qquad$

The use of .FILTER allows to define the objective waveform as a subset of the global .DATA which may have been automatically generated by another tool.

Reserved keywords for internal quantities are:

| ISTEP | for the index of the current step (first index is 0) |
| :--- | :--- |
| ICARLO | for the index of the current Monte-Carlo run (first index is 0) |
| IALTER | for the index of the current .ALTER (first index is 0) |
| ITEMP | for the index of the current temperature value (first index is 1) |
| NBSTEP | for the total number of values generated by .STEP commands |
| NBCARLO | for the total number of Monte-Carlo runs |
| NBALTER | for the total number of .ALTER |
| NBTEMP | for the total number of temperature values |

## Parameters

- AC DC $_{\text {|TRAN }}$ | MODSST $\mid$ SST $\mid$ ALL

Specifies the analysis type.

- condition

For the filter of simulation syntax, if condition is false, then the corresponding analysis is bypassed. This is especially useful in the case of multiple simulations triggered by the presence of .DATA, and if only a few points of the data are of interest.

For the filter of extractions syntax, if condition is false, then the corresponding .EXTRACT or .meas is bypassed. If no label is given, all .EXTRACT and .meas commands are bypassed when condition is false.
For the filter of data syntax, condition should be a logical expression using only entries of the input . DAtA block. Each set of values will be evaluated. If condition is false, the set of values will not appear in the output .DAtA block. This is especially useful in case of optimization.

- LABEL=label

Specifies the label of a .EXTRACT or .meas.

- DATA_IN=input_data

Specifies the name of a .DATA statement.

- DATA_OUT=output_data

Specifies the name of the .DATA statement which will be created from the filtering of .DATA input_data.

## Examples

```
.TRAN O 100n sweep data = data_block
.FILTER all ptemp==27 && pvdd==3
.DATA data_block
+ ptemp pother pvdd res1 res2
+ 27 456 3 1e-5 1e8
+ 27 678 3.2 1e-5 1e8
+ 27 321 3.2 1e-5 1e8
+ 2712 3 1e-5 1e8
+ 27458 3.2 1e-5 1e8
.enddata
v1 1 0 pvdd
r1 1 0 1
.extract tran yval(v(1),0)
.end
```

In this example, simulation will be performed where ptemp=27 and pvdd=3. This corresponds to the fourth entry of the .DATA block. All other simulations will be bypassed.

```
.STEP PARAM p1 1 10 1
.EXTRACT tran label=FOO max(v(1))
.FILTER EXTRACT LABEL=FOO {p1 >= 3}
```

This example filters extractions, when $\mathrm{p} 1>=3$ the corresponding .EXTRACT is taken into account.

```
.option OPSELDO_OUTER
.TEMP -10 27 50
.TRAN 1n 100n
.FILTER data data_in=IIN data_out=OON {abs(ptemp-temper)<1e-5}
.objective tran label=fit_out V(S) GOAL=OON(VS)
```

```
.data IIN x ptemp vs
+ 10n -10 5.142e-5
...
+ 20n -10 1.023e-1
+ 30n -10 7.175e-1
+ 40n -10 1.025
+ 50n -10 1.018
+ 60n-10 9.710e-1
+ 70n -10 3.717e-1
+ 80n -10 -5.221e-2
+ 90n -10 1.674e-3
+ 100n -10 2.031e-3
+ 10n 27 5.955e-5
+ 20n 27 1.463e-1
+ 30n 27 9.377e-1
+ 40n 27 1.051
+ 50n 27 9.956e-1
+ 60n 27 9.556e-1
+ 70n 271.503e-1
+ 80n 27-3.140e-2
+ 90n 27 5.975e-3
+ 100n 27 -1.336e-4
+ 10n 50 6.450e-5
+ 20n 50 6.155e-2
+ 30n 50 4.499e-1
+ 40n 50 7.884e-1
+ 50n 50 9.671e-1
+ 60n 50 1.019
+ 70n 50 7.394e-1
+ 80n 50 3.579e-1
+ 90n 50 6.591e-2
+ 100n 50 -4.888e-2
.enddata
```

This example shows the filter of data. In this example three optimizations are required, one for each temperature.

## .FORCE

## Initial Transient Analysis Conditions

```
.FORCE [NODE] {node_name value}
+ [IND|OBJ] {object_name value}
```

Forces one or more nodes to specified voltage(s) with respect to ground for the initial transient solution. This is similar to the .IC command, values will be used only for the DC performed prior to TRAN analysis. Both commands are used to give values replacing the DC solution. With the .FORCE syntax, initial values of inductors current can be given while with . Ic only node voltages can be initialized including nodes inside subcircuits.

If the UIC parameter is also present (in the .TRAN command) no DC analysis is performed and the voltages are initialized as defined in the . FORCE command. All other voltages on nodes not initialized in the .FORCE command are determined by Eldo itself. During subsequent analysis (transient), the node voltages are freed of their initial values, and may therefore assume different values.

## Parameters

- node_name

Node name.

- value

Value at node.

- IND|OBJ

Inductor or object. For objects, only voltage source components can be specified to set the current on.

- object_name

Inductor or voltage source component.

## Example

```
V1 1 0 pwl(0 0 10n 5v)
R1 1 2 1k
C1 3 0 100p
L1 2 3 1u
.force ind L1 10mA
.tran 1n 0.1u uic
.plot tran i(L1)
.plot tran v(3)
.end
```


## .FOUR

## FFT Select Waveform

.FOUR LABEL=label_name waveform_name [optfour_parameters]
Selects the waveform on which you require FFT to be done. This command also accepts signals, for example . FOUR $s g(y c o r e->A(0))$.

Options for the FFT post-processor can be specified inside this command or through the .OPTFOUR command, see ".OPTFOUR" on page 764.

## Parameters

- label_name

Reference name used by Eldo to select which wave has to be plotted (.рцот) or on which FFT wave extraction of useful quantities has to be done (.EXTRACT). label_name is required.

- waveform_name

Any regular Eldo waveform name: there can be any number of .FOUR commands specified in the .cir file.

- optfour_parameters
.OPTFOUR command parameters can be specified here. This allows calculation of multiple FFTs in a single simulation. If no additional arguments are provided, the .FOUR command uses the default setting of . OPTFOUR parameters.


## Examples

```
.FOUR LABEL = t1 V (a)
.FOUR LABEL = t2 W('V(a) - v(b)/2.0')
.FOUR LABEL=foo1 v(ofdm).h(1)
+ tstart=modsst_fft_tstart1 tstop=modsst_fft_tstop1
+ nbpt=48 normalized=1 interpolate=0
+ display_input=1
```

The last example shows the specification of . OPTFOUR command parameters inside the .FOUR command. This allows calculation of multiple FFTs in a single simulation.

## Display and .EXTRACT of FFT results

[.PLOT |.PRINT|.PROBE ] FOUR FOURxx (label_name)
.EXTRACT FOUR <expression>
xx stands for $\mathrm{DB}, \mathrm{R}, \mathrm{I}, \mathrm{P}, \mathrm{m}$.

## Examples

```
.FOUR LABEL = t1 V(a)
.PLOT FOUR FOURDB(t1)
```

It is also possible to extract values from a FFT waveform:

```
.FOUR LABEL = t1 V(a)
.EXTRACT FOUR YVAL (FOURDB(t1),5MEG)
```

Eldo will print out the value (in dB ) at 5 Meg for the FFT done on $\mathrm{v}(\mathrm{A})$.

## .FUNC

## User Defined Function

. FUNC $P(a, b, \ldots)$ EXPR
This command is used to define functions used in expressions. They are flexible and useful when there are several similar sub-expressions in a circuit file.

This command provides compatibility with PSpice. It is equivalent to the .PARAM user-defined function specification.

## Parameters

- $P(a, b)$ EXPR

Specifies a user-defined function in order to define a parameter using an expression. The parameter may then be called when required.

## Example

```
.func P(a,b) expression
R1 1 2 'P(a,b)'
```


## .GLOBAL

## Global Node Allocation

.GLOBAL NN \{NN\}
Declare global node(s), making them known throughout a circuit without having to declare them in each subcircuit. The number of such nodes is unlimited. .global is active when placed anywhere in the netlist. This applies to any launch mode.

By default, nodes which appear in subcircuit definitions have priority over the nodes defined with . Global statements. It is exactly the opposite when option DSCGLOB=GLOBAL is specified (must be at the beginning of the netlist): nodes defined with .GLOBAL statements take priority over nodes which appear in subcircuit definitions.

## Parameters

- NN

Name(s) of the node(s) to be declared as global.

## Example

```
.global vdd vss
```

Specifies vdd and vss as global nodes throughout the circuit.

```
.global vdd mid
.subckt div1 mid
rl vdd mid 1k
r2 mid 0 1k
.ends
X1 net1 div1
r1 net1 0 1k
```

By default, Eldo will connect X1.r1 and X1.r2 to node net1. If option DSCGLOB=GLOBAL is set $\mathrm{X} 1 . \mathrm{r} 1$ and $\mathrm{X} 1 . \mathrm{r} 2$ will be connected to global node mid.

See also "DSCGLOB Option Example" on page 903.

## Related Option

DSCGLOB, see "DSCGLOB=X | GLOBAL" on page 976.

## .GUESS

## Initial DC Analysis Conditions

```
.GUESS V(NN)=VAL [SUBCKT=subckt_name] {V(NN)=VAL [SUBCKT=subckt_name]}
```

Helps to calculate the DC operating point by setting voltage values at selected nodes for the first iteration of a DC operating point calculation.

This command differs from the .nodeset command in so far as when using . guess the node voltages are only fixed for the first iteration of a DC operating point calculation, whereas when using .nodeset the node voltages are fixed for the duration of the first DC operating point calculation.

This command is useful when the approximate whereabouts of the DC operating point is known, enabling the simulator to converge more quickly.

## Note

By default, the first . guess specification has precedence over subsequent . quess specifications. Setting . OPtion Licn, the last . Guess specification will have precedence.

## Parameters

- $\quad \mathrm{V}(\mathrm{NN})=\mathrm{VAL}$

Voltage at node nn in volts.

- SUBCKT=subckt_name

If specified it will fix the voltage of the preceding node in all instances of the subcircuit subckt_name.

## Example

$$
\text { guess } \mathbf{v}(\mathrm{n} 4)=6 \mathrm{v} \quad \mathbf{v}(\mathrm{n} 5)=2 \mathrm{v} \quad \mathbf{v}(\mathrm{n} 6)=-5 \mathrm{v}
$$

Specifies that for the first iteration of a DC operating point calculation the voltages at the nodes $\mathrm{n} 4, \mathrm{n} 5$ and n 6 be set to $6 \mathrm{~V}, 2 \mathrm{~V}$ and -5 V respectively.

```
.guess v(2)=3v SUBCKT=sub1 v(4)=-2v SUBCKT=sub2
```

Specifies that for the first iteration of a DC operating point calculation the voltages at node 2 of subcircuit sub1 and node 4 of subcircuit sub2 will be set to 3 and -2 V respectively.

## .HDL

## Compile and Load Verilog-A Modules

.HDL FILE=filename [MODULE=module_name] [ALIAS=alias_name]
Compiles and loads Verilog-A modules in Eldo. The modules compiled with .hDL are instantiated in the same manner as Eldo subcircuits with names beginning with the "x" character. The module parameters can be provided on a .MODEL statement or on the module instance.

If only module_name is specified then module_name will be compiled from the file and loaded in the simulator. If in addition alias_name is specified then any reference to module_name must be done using alias_name instead of module_name.

In addition to the . HDL command, three related command line flags and three related options are available: -hdlpath, -spmodel, -vamodel and SPMODEL, VAMODEL, VAOPTS.

Refer to the Eldo Verilog-A User's Manual for further information.

## Parameters

- FILE=filename

Verilog-A file.

- MODULE=module_name

Module name. Optional. If specified, only that module is loaded from the specified
Verilog-A file.

- ALIAS=alias_name

Specifies an alias instead of the module name defined in the Verilog-A file. Optional. This could be useful if you want to load modules of the same name from different source files.

## Examples

```
.hdl mos.va
.model myjfet jfet lambda=0.01
x1 d g s myjfet vt0=-2.0 beta=1.0e-4
```

Loads the mos.va Verilog-A file.

```
.hdl mos_ideal.va module=jfet alias=ideal_jfet
.hdl mos_simple.va module=jfet alias=simple_jfet
x1 d1 g1 s1 ideal_jfet vt0=-2.0 beta=1.0e-4 lambda=0.01
x1 d2 g2 s2 simple_jfet vt0=-2.0 beta=1.0e-4 lambda=0.01
```

Shows how the same module name in two different source files can be loaded using the alias_name parameter.

## Related options

```
"MACMOD=[1|2| 3|0]" on page 954, "SPMODEL=subckt_name" on page 1020,
"VAMODEL=mod_name" on page 1020, and "VAOPTS=options_string" on page 1021
```

Related command-line flags
"-hdlpath veriloga_path" on page 48,
"-spmodel <subckt_name1> -spmodel <subckt_name2> ..." on page 54, and
"-vamodel <mod_name1> -vamodel <mod_name2> ..." on page 56

## -compat flag

In -compat mode, the syntax is different:
.HDL "filename" [module_name] [module_alias]

## .HIER

## Changing the Hierarchy Separator

```
.HIER .|/|<char>
```

By default the hierarchical separator in Eldo is the '.' character. The Verimix interface imposes the use of the '/' character for the hierarchical separator. Therefore, for Verimix integration, '/' is allowed as the hierarchical separator.

Please refer to ".A2D" on page 528 and ".D2A" on page 577.

The rule defined in "Hierarchical Management" on page 681 applies, however, the hierarchical separator differs.

There is no impact on the Eldo naming convention. In the Eldo description part, all the hierarchical names use the default hierarchical separator (by default '. '). To change the hierarchical separator in Eldo, use the .hIER command, for example the line:

```
.HIER /
```

changes the default hierarchical separator '.' to '/'.

- char

It is possible to specify any character as the hierarchical separator. However, care must be taken as there may be possible side effects. One restriction is that this character should not appear elsewhere in instance or net names.

Example for the .A2D command with Verimix:

```
in the eldo description part | in the verilog description part
XIC1 OUT1 OUT5 My_Subckt
. SUBCKT My_Subckt IN OUT
    .A2D digital_name eldo_name
+MOD=model_a2d
.ENDS My_Subckt
\$vmx_define_export(test.top.ic1.out2,
                            "XIC1/DIGITAL_NAME");
```

The hierarchical name of the eldo node eldo_name is XIC1.DIGITAL_NAME. In this case the name sent from Eldo to the Verimix interface is XIC1/DIGItal_NAME.

Example for the .D2A command in Verimix:

```
in the eldo description part | in the verilog description part
```



In this case the name sent from Eldo to the Verimix interface is XIC1/DIGITAL_NAME.

## Note

If the subcircuit My_Subckt is instantiated in another subcircuit, the hierarchical name will look like < . . . >/XIC1/DIGITAL_NAME.

## Hierarchical Management

The hierarchical management for the digital_name, which is implicitly generated from the eldo_name by Eldo is allowed. To allow hierarchical netlist generation, the implicit digital_name generated by Eldo for the synchronizer takes into account the hierarchical context, for example:

```
XIC1 OUT1 OUT5 My_Subckt
...
.SUBCKT My_Subckt IN OUT
..
    .A2D eldo_name
    +MOD=model_a2d
...
.ENDS My_Subckt
```

The hierarchical name of the Eldo node eldo_name is XIC1.eldo_name. However, the implicit digital_name sent to the synchronizer is XIC1.ELDO_NAME and not eldo_name.

## .IC

## Initial Transient Analysis Conditions

```
.IC V(NN)=VAL [SUBCKT=subckt_name] {V(NN)=VAL [SUBCKT=subckt_name]}
```

Used to fix node voltages for the duration of a DC analysis. If the UIC parameter is also present (in the .TRAN command) no DC analysis is performed and the voltages are initialized as defined in the . Ic command. All other voltages on nodes not initialized in the . Ic command are determined by Eldo itself. During subsequent analysis (transient), the node voltages are freed of their initial values, and may therefore assume different values.

The . Ic command on devices is interpreted only on C and L devices. For all other devices, the .IC command is ignored.

By default, Eldo behaves like Spice 2 g 6 regarding . Ic commands and Ic parameters specified on devices: . Ic commands are taken into account only for DC done before Transient analysis, or when .TRAN . . . UIC is specified. However, IC parameter specifications on devices are taken into account only in the case of .TRAN ... UIC. Specify option ICDC for . IC commands (and IC parameter specifications on devices when option ICDEV specified) to be taken into account for any DC analysis. Specify option ICDEv for IC parameters specified on devices and . Ic commands to be handled the same way.

## Note

By default, the first IC specification has precedence over subsequent IC specifications. Setting option LICN, the last IC specification will have precedence.

## Parameters

- $\mathrm{v}(\mathrm{NN})$

Voltage at the node nN in volts.

- SUBCKT=subckt_name

If specified it will fix the voltage of the preceding node in all instances of the subcircuit subckt_name.

## Examples

$$
\begin{aligned}
& . d c \\
& . \text { ic } v(2)=3 v \quad v(4)=-2 v
\end{aligned}
$$

Specifies that for the duration of the DC analysis, the voltages at the nodes 2 and 4 be fixed to 3 and -2 V respectively. Other circuit node voltage values are computed by Eldo.

```
.tran 1ns \(100 n s\) uic
.ic \(v(n 3)=7 v \quad v(n 4)=2 v \quad v(n 5)=-3 v \quad v(x 1.222)=0 v\)
```

Specifies that no DC analysis should be performed and that at the beginning of the transient analysis the voltages at the nodes $\mathrm{n} 3, \mathrm{n} 4$ and n 5 be set to $7 \mathrm{~V}, 2 \mathrm{~V}$ and -3 V respectively, while node 222 of subcircuit $x 1$ is set to 0 V . Other node voltages are calculated by Eldo.

```
.dc
.ic v(2)=3v SUBCKT=sub1 v(4)=-2v SUBCKT=sub2
```

Specifies that for the duration of the DC analysis, the voltages at node 2 of subcircuit sub1 and node 4 of subcircuit sub2 will be fixed to 3 and -2 V respectively. Other circuit node voltage values are computed by Eldo.

## Related options

"ICDC and ICDEV" on page 978; "LICN" on page 979; "NOLICN" on page 981.

## .IGNORE_DSPF_ON_NODE

## Ignore DSPF on Specified Node

.IGNORE_DSPF_ON_NODE \{NODE\}
Used to force Eldo to ignore parasitic elements on a specified node when a DSPF file has been included using the .DSPF_INCLUDE command. All parasitics attached to the specified node will be removed: those inside the specified node (net) and those detailed inside a different node but connected to the specified node.

This command is ignored when DEV=DSPF is specified on the .DSPF_INCLUDE command.

## Parameters

- NODE

Specifies node(s) for which the parasitics given in the DSPF file will be ignored.

## Example

```
.DSPF_INCLUDE testspf.spf
.IGNORE_DSPF_ON_NODE n1 n2
```

For nodes n1 and n2 parasitics as specified in DSPF file testspf.spf will be ignored.
In the example DSPF file snippet below, if .IGNORE_DSPF_ON_NODE N1 is specified Eldo ignores the coupling capacitance CC1. This is because it connects to the N1 net even though it is detailed inside the N2 net.

```
* NET N1
* S N1:1
C1 N1:1 0 0.02p
* NET N2
* S N2:1
CC1 N2:1 N1:1 0.01p
```


## .INCLUDE

## Include a File in an Input Netlist

. INC [LUDE] FNAME
Inserts the contents of a file into a circuit description file. Including a file is the same as typing the included file's text directly into the circuit description file. Included files may not contain title lines (comments may be used). A . END statement in an included file marks only the end of the included file.

Eldo searches for the specified file in a specific order. This works in the same way as the . IId command:

1. Absolute path
2. Parent directory

Directories of the files in the calling hierarchy (files which contain the . Include/. LIb statement), the directory of the last calling file being searched first
3. Current directory

Directory from which Eldo was started
4. Search path

Specified using the -searchpath flag or . Option Search=path within the netlist. If both are specified, then the contents of -searchpath is searched first.

## (i) For more information see "Search path priorities" on page 694.

Nesting of . include commands is allowed. . include files are included only once even if the . include statement appears several times. However, when the . include is located inside a SUBCKT, the inclusion will occur.

The . INCLUDe command can also be used to include DSPF files that contain the complete netlist (active elements and parasitics). Subcircuits can be instantiated using either the .TOPCELL command or an $x$ instance.

Use option Continue_include to specify that continuation lines with + as the first character apply to the . include command in the file.

To replace one file by another one when using the Eldo re-run facility, use the option altinc. This forces Eldo to replace the first . include statement found in an input netlist by the first . include statement found in the .alter section of the netlist.

By default the content of . Include commands specified in . ALter blocks is treated by Eldo as if the content is written at full length in the netlist and substitutes accordingly. In previous versions (pre-v6.9), the . INCLUDe commands specified in .ALTER blocks were added
(extended) to the nominal circuit. For backward compatibility, specify option noaltincex to switch back to this mechanism.

## Related Options

altinc, see "Altinc" on page 951, continue_include, see "CONTINUE_INCLUDE" on page 952, NOALTINCEX, see "NOALTINCEX" on page 955,.

## Parameters

- FNAME

Name of the file to be included. This name may be any character string which is a legal path name. The filename can be written in either upper or lower case letters. It is possible to have a mixture of both.

## Examples

```
.INCLUDE circuit_add_on.cir
```

Specifies that the contents of the circuit_add_on.cir file be included in the circuit description file. In this case, the included file is resident in the same directory as the circuit description file.

```
.INCLUDE /users1/examples/circuit2.cir
```

Specifies that the /usersl/examples/circuit2.cir file is to be included in the circuit description file.

```
TITLE
.INCLUDE foo
.INCLUDE foo !this include will be ignored.
...
.END
```

In the example above, the second .include statement is ignored.

```
TITLE
.SUBCKT S1..
    .INCLUDE foo
.ends
.SUBCKT S2
    .INCLUDE foo
.ends
.end
```

In the example above, the file named foo will be included twice. The . include statements have been located inside subcircuits.
The following example shows how to specify that continuation lines with + as the first character apply to the . Include command in the file. If the main netlist has the two lines:

```
.include file.inc
+ b=2
```

With the continue_include option specified, if file file.inc contains as its last line:

```
.param a=1
```

Eldo would interpret this as:

```
.param a=1
+b=2
```

The following example shows how to replace one included file by another one when using the Eldo re-run facility, with the option altinc. The new_models file will be included in the re-run simulation instead of models.

```
.include models
.option altinc
r1 1 0 rval
v1 1 0 dc 1
.extract dc i(r1)
.dc
.alter
.include new_models
```

By default the content of . include commands specified in . Alter blocks is treated by Eldo as if the content is written at full length in the netlist and substitutes accordingly. In previous versions (pre-v6.9), the . INClude commands specified in .ALTER blocks were added (extended) to the nominal circuit, for example:

```
i1 1 0 1
r1 1 0 1
.op
.extract dc v(1)
.alter
.include altincex.a1
.end
```

assuming file altincex.al contains the line r1 10 2, for the first ALTER run Eldo will substitute r1 101 by r1 102 in the netlist (behaves as if line r1 102 was in the netlist). For Eldo versions before v6.9, Eldo assumed two resistors in parallel to the I1 device. For backward compatibility, specify option noaltincex to switch back to the old mechanism.

## .INIT

## Initial Digital Circuit Conditions

```
.INIT NODE [DC=VAL] TI TS VALI {TI TS VALI}
```

This command is used when initializing digital circuits. Between the times TI and TS, Eldo forces the node NODE to the voltage level specified by VALI. If a DC value is also specified, the simulation is started with the specified value assigned to the node. Outside the specified time limits the node is computed as a normal node.

## Parameters

- NODE

The name of the node to be initialized with a voltage level.

- TI

The time from which the node is to be initialized to the specified voltage level.

- TS

The time beyond which the voltage initialization on the node should be stopped.

- VALI

The voltage level to which the node should be initialized, in volts.

- $\mathrm{DC}=\mathrm{VAL}$

Voltage level to which the node should be initialized at the start of the simulation period. Optional.

## Example

$$
\text { .init n1 dc=2 5u 10u } 5
$$

Specifies that the node n 1 be initialized to 5 V between the time period 5 and $10 \mu \mathrm{~s}$. The node is initialized to 2 V at the start of the simulation.

## .IPROBE

## Current Probe

.IPROBE LABEL=vname [DIRECTION=POS|NEG ] pinref1 \{pinrefn\}
Use this command to probe current between pins. This is equivalent to inserting a zero voltage source between a node and a specified pin of a device. However it does not require netlist modification, which means for users working in a UI schematic environment, the netlister does not have to be run again.

Inserting a zero voltage source can be useful to measure current entering objects, or for some extra commands such as . LStb.

You can access the probed current with the expression IPROBE(vname).
IPROBE reports the SUM of the currents through the referenced pins. The "positive flow direction" is from the connection node into the device pin. Pins are referenced via the device pin INDEX number, for example r1.1 and r1.2 are the first pin of resistor r1 and the then second pin of resistor r 2 respectively. All referenced pins must connect to the same (possibly hierarchical) node. If there are N pins connected to a node, at most $\mathrm{N}-1$ pins can be specified in the pin list.

## Parameters

- LABEL=vname

Name of the voltage source to add. Current through this voltage source can be read using IPROBE (vname).

- DIRECTION=POS|NEG

This is pos by default. The voltage source is added between the original nodes referred to by the pinref list and a new node which will be created by Eldo, the name of which will be constructed from the prefix IPRB\# followed by vname. If direction is NEG, the voltage source is reversed.

- pinref

List of pin references connected to the same node. Syntax is device_name.pin_index. The number of pin references is not limited. All pin references must refer to the same original netlist, otherwise an error will be displayed. The pin references cannot make reference to ADMS devices, because such ADMS objects (Y instances) can be hierarchical devices, and this situation is not handled.

## Notes

. IPROBE is used to insert a current probe (zero voltage source) between a node and a selected number of pin objects. This pin list does not correspond to the pin list of the new zero voltage source. Imagine you have:

```
R1 A B 1k
R2 B C 1K
```

If you want to insert a current probe between R1 and R2, the syntax will be:

```
.IPROBE label = I R1.2
```

The following statement is incorrect:

```
.IPROBE label = I R1.2 R2.1
```

In both cases, Eldo will first create a new node named, for example, NEW. Eldo will then create a zero voltage source named, for example, VI. Eldo will connect node B to the first pin of VI, the second pin of I will be connected to NEW, and Eldo will then connect the pin list specified to the node NEW. With the first syntax above, only pin 2 of device R1 will be reconnected to NEW, but for the second syntax, both the second pin of R2 and the first pin of R2 will be reconnected to node NEW. In that second case, the original net $B$ will therefore be connected only to pin NEW, which is not what was required.

The equivalent netlist would be in case 1 :

```
R1 A B 1k
VI B NEW 0
R2 NEW C 1K
```

The equivalent netlist would be in case 2 :

```
R1 A NEW 1k
VI B NEW 0
R2 NEW C 1K
```

and $B$ here is a dangling node.

## Example

```
V1 1 0 1
r1 1 2 1
r2 3 1 1
r3 2 0 1
r4 3 0 1
r5 1 0 1
.dc
.IPROBE label=ux r1.1 r2.2
.print dc iprobe(ux)
.extract dc iprobe(ux)
```

The actual pin indicated by the pin reference list here is the node named " 1 ". It is the first pin of device R1 or the second pin of device R2. Eldo will insert a current probe (zero voltage source) between node 1 and a new node named iprb\#ux. The first pin of R1 and the second pin of R2 will be disconnected from node 1 and reconnected to the new node iprb\#ux. The $\operatorname{IPROBE}(\mathrm{UX})$ statement returns the sum of the current inside R1 and R2.

```
v1 1 0 1
r1 1 2 1
x1 2 3 foo
r3 3 0 1
.subckt foo 1 2
r1 1 2 1
.ends
.iprobe label=ip x1.1
.print tran iprobe(ip)
.tran 1n 5n
.end
```

This example shows how to insert a current probe with a subcircuit. Eldo will insert a zero voltage source between node 1 and a new node named IPRB\#IP. The first pin of subcircuit x1 will be disconnected from node 1 and reconnected to the new node Iprb\#Ip. The IPROBE(IP) statement returns the sum of the current inside x 1 .

```
v1 1 0 sin(0 1 1e9)
r1 1 2 1k
r2 2 3 1k
r3 2 0 1k
.tran 1p 1n
.iprobe label=test r1.2 r3.1
```

r 1 , r 2 , and r 3 are connected to node 2 . The iprobe command reports the total current through r1 and r 3 with current "direction" from node 2 into the pins.

## .LIB

## Insert Circuit Information from a Library File <br> ```.LIB [KEY=KNAME] FNAME [LIBTYPE]``` <br> .LIB LIBTYPE

This command is used to insert model or subcircuit definitions into an input netlist from a library file. Eldo includes the whole contents of the file specified. Although many subcircuits, models and parameters may be defined but not used, it is quicker than picking out the individual instances required.

If there are several definitions of the same instance defined in a block, Eldo will stop and produce an error message.

Nesting of . Lib commands is allowed. For more information on nested . Lib commands see "Library nesting" on page 695.

Eldo searches for the specified library file in a specific order. First it checks the directory the netlist is in, followed by the directory Eldo was started in, and then in the library file parent directory. For more information, see "Search path priorities" on page 694.

If a library file contains corners, the Libtype parameter is required in the netlist (see second syntax definition), otherwise Eldo will exit with an error. If a library file has been referenced without a corner, Eldo does not expect the syntax . Lib libtype inside the library file, and interprets all the . Lib commands as . ilb filename. Avoid this by referencing any library file containing corners with the Libtype parameter.

Libraries can be accessed directly from model and subcircuit description lines. This allows the properties of the model, or subcircuit, to be called from another file or directory. The syntax is as follows:

```
.MODEL LIB FNAME MNAME [LIBTYPE]
.SUBCKT LIB FNAME SNAME [LIBTYPE]
```

where MNAME and SNAME are the model or subcircuit names respectively.
It is also possible to use the . $\mathbf{\text { Lib command in interactive mode in SimPilot. See "Interactive }}$ mode" on page 695 for details.

If a parameter $P$ is referred to in a netlist but not defined, Eldo searches for $P$ in the . LIb files. Only global .PARAM definitions are considered. Parameter declarations within a . SUBCKT definition will not be considered outside that subcircuit.

## Parameters

- FNAME

Name of the library file to be searched. This name may be any character string which is a legal path name. FNAME must not end with <circuit_name>.lib or <circuit_name>_eldo.lib
since Eldo uses this type of filename for temporary files which are later deleted automatically by the Eldo script, that is, in the circuit file mycircuit.cir, the file mycircuit_eldo.lib must not be used.

## Note

A filename specified in the .LIB statement may be enclosed in single quotes to preserve compatibility with other simulators. When a character string is enclosed in single quotes, the case of the string remains unchanged, that is, no conversion to upper or lower case, allowing a mixture of the two.

- KEY=KNAME

Used in conjunction with the .ALTER or . STEP commands. KNAME is the key name used to identify the library files and variants (used in subsequent simulations) that may be replaced with the .alter command. For more information on the key parameter see the "Key parameter example" on page 696.

- LIBTYPE

Name of a library variant to be used. If a library file contains corners, this parameter is required for the . LIB statement in the netlist. For more information on library variants see "Library variant management" on page 694.

## Library management mechanism

A number of different mechanisms are available to manage libraries.
The library management changed in v5.8 compared to previous versions, in the way that the entire content of the selected library is included in the database. In pre-v5.8 versions, only the missing . SUBCKT, . PARAM or . MODEL definitions were extracted from the library.

In v5.9 and upwards, the change for v5.8 remains, but the .LIB command is acted upon immediately, that is, the content of the library is incorporated as soon as the command is parsed. In v5.8, the contents of the different libraries were incorporated only upon completion of reading the input file. In pre-v5.8 versions, libraries were re-read repeatedly to load missing definitions.

Note
$\square$ The pre-v5.8 version of library management is no longer supported.

An option, inclib, is available to use the alternate v5.8 mechanism.

## v5.8 mechanism

To use the Eldo v5.8 mechanism of library management, specify the option inclib.
With libraries containing thousands of definitions which are all likely to be used in a design, the procedure used in pre-v5.8 versions of Eldo, was far too slow. Specifying the v5.8 mechanism
means Eldo will include the whole content of the . LIB (or the full content of what is inside . LIb .ENDL blocks when variants are specified on the . Lib card). This procedure is faster, even if some models, subcircuits or parameters are defined but not used.

However, there are four side effects to this mechanism:

- When there are several definitions defined in the block that Eldo will include, the simulation will stop on error (previous versions accepted this but used only the first definition-it was however not safe to potentially have two definitions for the same entity).
- Eldo includes the full content of the . Lid card, which means Eldo interprets any commands/options which are specified in . LIB. With the pre-v5.8 implementation, these commands were not acted upon because they were not looked for.
- Parameters and models are defined in the order which corresponds to their order in the library. With the pre-v5.8 implementation, the order was the order of usage (first one used was the first one defined). Therefore, the Monte Carlo series associated to each entity will not be the same in both cases.
- If the filename specified in the . LIb does not exist, Eldo exits with an error.

In all cases, the content of what is actually included by Eldo appears in the ASCII output file.

## Search path priorities

The order of directories in which include and library files are searched for is:

1. Absolute path
2. Parent directory

Directories of the files in the calling hierarchy (files which contain the . Include/. imb statement), the directory of the last calling file being searched first
3. Current directory

Directory from which Eldo was started
4. Search path

Specified using the -searchpath flag or . OPtION SEARCH=path within the netlist. If both are specified, then the contents of -searchpath is searched first.

For more information on -searchpath, see "-searchpath path_list" on page 53 or "SEARCH=path1 [ \{: path2 \}]" on page 1022. For an example, see the "Search path priorities example" on page 696.

## Library variant management

Library variants such as best, worst, and typical process variation, may be handled using the following command:
.LIB FNAME LIBTYPE

Within the library fNAME, you must then have sections defined by:

```
.LIB <libtype>
..
.ENDL
```

For an example see the "Library variant management example" on page 697.

## Interactive mode

It is possible to use the .LIB mechanism in SimPilot. The netlist must contain one or several lines of type:
.LIB KEY=kname FNAME [LIBTYPE]
In interactive mode, the following commands can be issued:

```
.LIB key=toto mymod.tech nominal
.LIB key=toto mymod.tech worst
.LIB key=toto mymod2.tech
```

Eldo will search for the kname to identify which library must be replaced. Limitations of the . LIB command when issued in interactive mode are as follows:

- Subcircuits are not replaced.

When . uib is specified in the input file, it can be used to select a subcircuit to be included in the design. Since taking a subcircuit from another library than the library specified in the input file could result in a change of topology (and changing topology of the current design is strictly impossible), Eldo would issue an error whenever the user attempts to substitute one subcircuit for another.

- Switching between GUDM and non-GUDM models is prohibited. Similarly, switching between GUDM models is prohibited.
- Only MOS, BJT, DIODE, JFET, R, L and C .model commands can be substituted. Attempting to substitute other kinds of models will lead to an error.


## Library nesting

Eldo libraries may themselves contain other libraries. For example, consider a library lib.lib:

```
.lib best
.lib mos.lib best
.lib bip.lib best
.endl best
.lib typ
.lib mos.lib typ
.lib bip.lib typ
.endl typ
```

If a netlist contains the command:
.LIB lib.lib best
then Eldo will browse the mos.lib and bip.lib which are surrounded by .lib best and .endl best.

## Examples

The following example specifies that any model and subcircuit information missing in the input netlist should be taken from the file circuit1.cir.

```
.LIB circuit1.cir
```

The following example specifies that any model and subcircuit information missing in the input netlist should be used from the file circuit2.cir in the directory /users1/examples.

```
.LIB /users1/examples/circuit2.cir
```


## Search path priorities example

The following example is related to search path priorities and shows the order in which directories are searched. If you have the following command in a netlist file:

```
.LIB ./foo/myfile.lib
```

and if in the library file myfile.lib, you have:

```
.LIB toto
```

then if file toto is not found in the netlist directory or parent directory, it will be searched for in the current directory from which Eldo was started.

In the case of a nested . Lidb/. Include, it would search the directory of the library file containing the .LIB/. INCLUDE statement.

## Key parameter example

The example below demonstrates the use of the key parameter in conjunction with the .ALTER command.

```
.lib key=K1 /work/bip/mymod typ
.lib key=K2 /work/mos/mymod typ
...
.alter
.lib key=K2 /work/mos/mymod best
.alter
.lib key=K2 /work/private/mymod typ
.end
```

This command sequence causes three simulations to be performed always with library /work/bip/mymod typ. In the first simulation, library /work/mos/mymod typ is used. In the second simulation, library /work/mos/mymod best is used. In the third simulation, library /work/private/mymod typ is used.

## Library variant management example

The next example relates to Library variant management.
Library mos.lib:

```
.lib best
.model MN nmos level=3 vt0=0.5
.endl best
.lib typ
.model MN nmos level=3 vt0=0.75
.endl typ
.lib worst
.model MN nmos level=3 vt0=1.0
.endl worst
```

Circuit Netlist:

```
lib case management
.lib mos.lib typ
m1 vdd g 0 0 MN l=1.2U w=5U
vdd vdd 0 5
vg g 0 0.8
.op
.end
```


## .LOAD

## Use Previously Simulated Results

.LOAD [FILE=]filename
This command takes a set of voltages previously saved using the . SAVE command, and inserts these as .nodeset, . guess, or . Ic commands depending on how the LOAD file was created. It is also possible to have multiple occurrences of the .LOAD command in an input netlist.

This command works in a similar way to the . USE command. Simply, the attribute nodeset/ic/ guess need not be specified in the command since that information was dumped when creating the file with the . SAVE command.

```
(1) See also ".USE" on page 926.
```


## Parameters

- [FILE=]filename

Filename into which the DC values were saved via the .SAVE file_name DC command.

## .LOOP

## Insert a Feedback Loop

.LOOP INPUT OUTPUT [R|C|I|V VALUE] [DISCONNECT=DEV_NAME] [KEEPINPUT]
Inserts a feedback loop between the input and output nodes of an op-amp during transient analysis. This is, therefore, useful in obtaining both the Open and Closed loop characteristics of a circuit in the same simulation run. The following devices can be inserted in the feedback loop:

- Resistor.
- Capacitor.
- Independent Voltage Source.
- Independent Current Source.

If no device is specified, Eldo will insert a zero-voltage source between input and output. A second operation which is performed in the Closed-loop mode is to disconnect the voltage source ( $\mathbf{V}$ or $\mathbf{e}$ element) which is applied between node INPUT and GND, if present. This feature can be disabled using the keyword keepinput in the .LOOp command.

In addition to the above operation, a device which is active in Open-loop mode may be disconnected during simulation in Closed-loop mode using the disconnect keyword.

## Parameters

- INPUT

Input node of the operational amplifier which is to be connected in closed loop.

- output

Output node of the operational amplifier which is to be connected in closed loop.

- R

Keyword indicating a feedback loop with a resistive load.

- C

Keyword indicating a feedback loop with a capacitive load.

- I

Keyword indicating a feedback loop with an independent current source.

- v

Keyword indicating a feedback loop with an independent voltage source.

- VALUE

Value of the feedback device.

- DISCONNECT

Keyword indicating that a device in the feedback loop is to be disconnected.

- DEV_NAME

Instance name of the device in the feedback loop which is to be disconnected.

- KEEPINPUT

If specified, the voltage source ( $\mathbf{v}$ or $\mathbf{E}$ element) which is applied between node INPUT and GND will not be disconnected, if present.

Note $\qquad$
The AC analysis conditions defined in a netlist are always simulated prior to any transient analysis conditions in that same netlist.

## Example

```
r1 1 2 1k
c1 2 0 10p
c2 4 0 1p
r2 3 0 100
.model ampop opa level=2 voff=0 sl=50e06
+ cin=0 rs=10 vsat=5 gain=5000 fc=5000
v1 1 0 ac 1 pwl(4n 5 10n 0 20n 0 30n 5)
opa1 2 3 4 0 ampop
.loop 2 4 r 100
.ac dec 10 10e+4 10e+8
.tran 1m 100m
.plot ac vdb(4)
.plot tran v(4)
```

Specifies that during transient analysis of the circuit, a resistive load of $100 \Omega$ is inserted between the input node 2 and output node 4 of opa1. During AC analysis, no feedback loop is inserted between these nodes.

## Note

The definition of two voltage sources v1 in the netlist. Eldo uses the AC voltage source
definition for the AC circuit analysis and the transient voltage source definition for the
transient circuit analysis.

## .LOTGROUP

## Share Distributions

.LOTGROUP group_name[/distrib_type]=val[\%]
This syntax allows different entities to share the same distribution.
Anywhere Eldo accepts LOT or Dev specification, one can specify LOTGROUP=group_name.

## Parameters

- group_name

Name of group.

- distrib_type

This can be one of the following options:

## UNIFORM

Uses a uniform distribution (default).

## GAUSS

Uses a Gaussian distribution.
<dist_name>
Selects a user defined distribution named dist_name.
If no distribution type is selected, it will default to UNIFORM.

## Examples

```
.LOTGROUP my_lot_group=14%
.LOTGROUP my_lot_group/uniform=14%
.LOTGROUP my_lot_group/gauss=12%
.LOTGROUP my_lot_group=(nor,-12%,10%)
.LOTGROUP my_lot_group/my_distrib_name=8%
```

This works together with:

```
.DISTRIB my_distrib_name (-1,0) (-1,0.5)
+ (-0.4,0.5) (-0.4,0)
+ (0.4 0) (0.4 0.5)
+ (1 0.5) (1,0)
```

For more information see ".DISTRIB" on page 614.

All entities which refer to the same "lotgroup" will share the same distribution.

```
.LOTGROUP my_lot_group=14
.MCMOD MOD1 TOX LOTGROUP=my_lot_group
.PARAM P1=1 LOTGROUP=my_lot_group
```

In this example, the same random number, between +14 and -14 , will be used for updating P1 and rox of model MOD1.

## .LSTB

## Loop Stability Analysis

.LSTB SOURCE_NAME
This command improves the analysis of circuit stability. The classical method for stability analysis is to break the feedback loop at an appropriate point on AC analysis, while maintaining correct DC conditions. This means that the loop must be terminated with the appropriate impedance it 'sees' looking at the loop input. Obtaining this impedance value is not always a simple task.

The . LStb command measures the loop gain by successive injection (Middlebrook Technique). A zero voltage source is placed in series in the loop: the first pin of the voltage loop must be connected to the loop input, the other pin to the loop output. The name of this voltage source is given in the . цStb card, and the loop gain can be displayed using keywords LSTb_db, LSTb_P, LSTB_R, LSTB_I, LSTb_M (see meanings in table below) in any .PLOT/.PRINT/ .PROBE/.EXTRACT commands.

Table 10-15. LSTB Output Formats

| Format | Meaning |
| :--- | :--- |
| DB | Magnitude in dB |
| $\mathbf{M}$ | Magnitude |
| $\mathbf{P}$ | Phase |
| $\mathbf{R}$ | Real part |
| I | Imaginary part |

## Example

aopstb.cir (provided in: \$MGC_AMS_HOME/examples/eldo/)—this circuit is derived from aopbou.cir and aopalt.cir which are also provided.

- Split node $S$ into node $S$ and $S L$, and insert the VSTB source:

```
M7 B SL C VSS mod1 W=130U L=4U
VSTB SL S
```

- Invoke LSTB analysis:

```
.LSTB VSTB
```

- Output the LSTB analysis:

```
.plot ac lstb_db
.plot ac lstb_p
```


## .MALIAS

## Model and Subcircuit Name Mapping

. MALIAS actual_name alias_name
This command can be used to map a model (or subcircuit) name in a netlist to a model (or subcircuit) name specified in a .model (or . Subckt) statement. This is similar to the .DEFMOD command, except the arguments are reversed.

The mapping works if the .MALIAS is placed before any use of the string alias_name.

## Parameters

- actual_name

Model name defined in .model statement, or subcircuit name defined in .subckt statement.

- alias_name

Model (or subcircuit) name specified in a netlist.

## Example

$$
\begin{aligned}
& . \text { model model1 } \mathrm{r} \text { tc } 1=2 \text { tc } 2=1 \\
& \text {.malias modell modalias } \\
& \text { r1 } 0 \text { modalias } r=1 \mathrm{k}
\end{aligned}
$$

Model name model1 is aliased to modalias.

```
.subckt myres in out rr=1
r1 in out r=rr
.ends
.malias myres myres_alias
x1 in out myres_alias r=20k
```

Subcircuit name myres is aliased to myres_alias.

## .MAP_DSPF_NODE_NAME

## Map Eldo Node to DSPF Node

```
    .MAP_DSPF_NODE_NAME LOGICAL=ELDONAME DSPF=NEWNAME
```

This command can be used if the DSPF file specifies for a node to be replaced causing references to nodes in commands such as .РLOT, .PROBE and .EXTRACT to become unusable. Eldo will map all of the node references to the new DSPF node name. For information on loading DSPF files see ".DSPF_INCLUDE" on page 617.

## Parameters

- LOGICAL=ELDONAME

Name of node to be mapped.

- DSPF=NEWNAME

DSPF node name to replace all references to eldoname.

## .MC

## Monte Carlo Analysis

```
.MC RUNNO [OUTER] [OV] [SEED=integer_value] [NONOM] [ALL]
+ [VARY=LOT|DEV] [IRUN=val] [NBBINS=val] [ORDMCS] [MCLIMIT]
[PRINT_EXTRACT=NOMINAL|ALL|run_number] [SIGBIN=val]
[MAXABSBIN=val] [MAXRELBIN=val]
[MONITOR] [AUTOSTOP=expression]
+ [SAVE=mc_file] [RESTART=mc_file]
```

Please refer to the Monte Carlo Analysis chapter for further information.

The Monte Carlo system may be implemented for DC, AC and transient analysis and is useful to obtain statistical information derived from estimates of the random variability of all circuit components. Model parameters may be specified with nominal and tolerance values. The Monte Carlo analysis system carries out multiple simulation runs, each run using model and device values differing from the nominal one within the specified tolerance limit, the variation being a simulated random variable satisfying a specified distribution (uniform, Gaussian, or userdefined).

This kind of analysis is useful in yield prediction and synthesis. When Monte Carlo analysis has been requested, information is added to each item plotted or printed regarding minimum and maximum values.
.MPRUN can be used to take advantage of multi-processor machines for the .mC command. Please see ".MPRUN" on page 729 for further information.

The keyword, statistical $=0 \mid 1$, can be specified on X instances, device declarations, or on . Subckт definitions, to specify whether any statistical variation due to Monte Carlo analysis can be applied to the specified entities. If statistical is 0 , the selected devices will keep their nominal values. If statistical is 1 , the selected devices have statistical variation applied. The global default can be specified via option statistical $=0 \mid 1$. Default is 1 .

The standard deviation is calculated for the output specified in the .mc command for each Monte Carlo run. At the end of the Monte Carlo analysis, a print-out is made of the worst case value. Furthermore, all the Worst Case model parameters, together with the values of the dipoles are printed.

Two standard deviation results are provided: "standard deviation" is the RMS value of the deviation of output with respect to the average value; "standard deviation based on nominal run" is the RMS value of the deviation of output with respect to the nominal run.
$(\text { standard deviation based on nominal run })^{2}=$
$(\text { standard deviation })^{2}-(\text { nominal value })^{2}+(\text { average value })^{2}$
Note
Multiple sensitivity and statistical analyses cannot be used simultaneously. Specifically,
.MC, .DCMISMATCH, and . WCASE are exclusive. Only one of them can be specified in a
netlist. Additionally, the .MC command may not be used in a netlist together with
transient noise analysis (.NOISETRAN).

The results of Monte Carlo analysis runs are output using the .EXTRACT, .PRINT and .PLOT commands.

By default, .mc used without the all keyword disables option probeop, option probeop2, and PSF OP information. Use option MC_NOMINAL_OP to save OP results for the nominal run.

## Parameters

- Runno

Number of simulation runs.

- outer

When there are both .step and .mc commands, Eldo performs a full Monte Carlo analysis for each point of the . STEP command. If the keyword outer is specified on the .MC command the nesting of the simulations will be inverted. Instead, a . Step will be performed at each Monte Carlo run (the outer keyword must be placed after the specification of the number of Monte Carlo runs). .mC outer does not work with a variation in temperature with the .TEMP command (for example .TEMP $0 \quad 39$ 80) or . STEP TEMP command, but does work with a single temperature definition with .TEMP (for example .TEMP 70).

- ov

Requests the output of a node voltage or current through a voltage source. These output values are used as reference for the Worst Case analysis.
The syntax for the voltage or current output is as follows:
I (Vxx[, Vyy])
Specifies the current difference between the voltage sources $\mathbf{v}_{\mathrm{xx}}$ and $\mathbf{v}_{\mathrm{yy}}$. If $\mathrm{v}_{\mathrm{y}}$ and the comma are omitted, the current through $\mathrm{vxx}^{\mathrm{xx}}$ will be printed.
v(N1[, N2])
Specifies the voltage difference between nodes N1 and N2. If N2 and the preceding comma is omitted, ground is assumed.
The following AC analysis output commands are also available:

```
VDB(N1[, N2]) IDB(Vxx[, Vyy]) IGD(v_source)
VI(N1[, N2]) II(Vxx[, Vyy]) VGD(node_name)
VM(N1[, N2]) IM(Vxx[, Vyy])
VP(N1[, N2]) IP(Vxx[, Vyy])
VR(N1[, N2]) IR(Vxx[, Vyy])
```

For each run, Eldo computes the standard deviation on the ov quantity and outputs it in the ASCII output file. The standard deviation (sigma) is computed in the following manner:

For transient simulation:
sigma $=$ SUM(delta*delta*h) / TMAX
where delta is the difference between ov for nominal run and current run at current step, $h$ is the time step for current step, and tMAX is the transient simulation duration.

For other analyses:
sigma $=$ SUM(delta*delta) / nbpt
where nbpt is the total number of points in the simulation.
At the end of the MC simulation, Eldo indicates the run that generated the worst standard deviation as the worst case conditions in the ASCII output file. Here is an example of the output in the .chi file:

```
Standard Deviation for run 1: 1.621303E+00
Standard Deviation for run 2: 2.016042E+00
Standard Deviation for run 3: 8.805810E-02
Worst Case Conditions: Run Number 30
```

- SEED=integer_value

This number is used to initialize the pseudo-random sequence of numbers. Running the .mC analysis twice with the same seed specified will provide the same simulation results.

- NONOM

Nominal run for Monte Carlo analysis is bypassed. This option is used by Accusim. When nonom is active, the ALL option of .MC is enabled as well.

- all

If this optional parameter is declared, the waveform results of every Monte Carlo simulation run are stored in the output files (one set per RUNNo) in contrast to the usual nominal, maximum and minimum results.

- VARY=LOT $\mid$ DEV

Specifies that only a Lot or DEv specification is taken into account. When specifying dev then dev and devx variation is taken into account. Only one vary specification can be set. By default, Eldo applies Lot, dev and devx variation.

- IRUN=VAL

Can be specified if a single, specific run, of a Monte Carlo analysis is required. VAL is an integer. Runno is still required to be specified, even though it is not used in that mode.
Example:
.MC 10 IRUN=3

Eldo will run a single analysis which corresponds to the third Monte Carlo analysis of the ten run series. If IRUN $\leq 0$ it will be ignored and a warning generated.

- nBBINS=VAL

Specifies the number of bins for the histogram produced when Monte Carlo analysis is used with . Extract statements. Default is 10 .

- ORDMCS

Determines whether multiple MC parameters in the simulation share the same pseudorandom probability values or not. See ORDMCS in the Monte Carlo Analysis chapter for usage examples.

- mClimit

Specifies that all parameters with statistical distribution (DEv, DEvx, or LOT) will have their distribution modified to one of two deviation values. These values correspond to the maximum deviation of the original distribution as defined by the option SIGTAIL. For example, a parameter with a nominal value of 1.0 , a statistical deviation of $\mathrm{DEV} / \mathrm{GAUSS}=5 \%$, and with option sigtail at its default value of 4 , the two values will be calculated as follows:

$$
1-(4 * 0.05)=0.8, \quad 1+(4 * 0.05)=1.2
$$

This functionality can be useful to force Monte Carlo runs to use maximum deviation combinations. MCLIMIT affects all statistical parameters whatever their original distribution.

- PRINT_EXTRACT=NOMINAL $\mid$ ALI $\mid$ run_number

Specifies for which run extracted values should be printed and written to output files.
nominal
Only the nominal extracted value is printed (default).
aLl
Extracted values are printed for all runs.

```
run_number
```

Extracted values are printed only for the specified run_number ( 0 is the nominal run).

- $\operatorname{sig}$ bin=VAL

Can be specified to truncate the histogram to a certain number of sigmas. Eldo will gather all the samples above "mean+SIGBIN $\times$ sigma" in the Above bin, and all the samples below "mean-SIGBIN $\times$ sigma" in the Below bin. This might be useful when there are a few untypical samples that would otherwise corrupt the min and max of the histogram.

- MAXABSBIN=VAL

Can be specified to simplify the histograms printed out in the .chi file, if they are difficult to read if most of the samples are in the same bin. If there are more than MAXABSBIN terms in a bin, then that bin will be expanded recursively, and a new histogram will be printed out
for that bin. This corresponds to a zoom in each of the bins which contain too much samples. Default value is -1 , that is, this option is not active by default.

- Maxrelbin=Val

Can be specified to simplify the histograms printed out in the .chi file, if they are difficult to read if most of the samples are in the same bin. If there are more than MAXRELBIN\% of the samples in the same bin, then that bin will be expanded recursively, and a new histogram will be printed out for that bin. This corresponds to a zoom in each of the bins which contain too much samples. Default value is -1 , that is, this option is not active by default.

- MONITOR

Monitor the evolution of certain quantities. Eldo will flush out from the . $w d b$ file the average and standard deviation of extracts (.EXTRACT) and measurements (.MEAS) versus the Monte Carlo run index in order to see how these entities evolve. Eldo will also flush out of the.$w d b$ file the expressions used in the Autostor criteria.

- AUTOSTOP=expression

Automatically stops the Monte Carlo process based on the convergence of some or all of the quantities defined in the expression. The expression in the aUtostor clause is a boolean expression using the mCconv extracts as described in "Monte Carlo Convergence" on page 1218.

- SAVE=mc_file

Saves any relevant information to a specific file. This files can then be used start a new session inheriting the results from the saved session. This save feature is disabled when multiple run commands are specified (.STEP, multiple .TEMP, .AGE, and .MPRUN).

- ReStart=mc_file

Restarts a Monte Carlo simulation run from a previous session on the same design saved with the .MC ... SAVE=mc_file specification. If the file, mc_file, does not exist Eldo generates a warning and performs a normal Monte Carlo run. If a restart file is specified, it means that the number of runs indicated on the command is the additional number of runs.

Topology or stimuli condition changes are allowed, but are not meaningful. The histogram and Monte Carlo statistics reported at the end of an incremental Monte Carlo "session" are computed using data from the previous session. The waveforms displayed versus the run index display the total information, that is, combine the successive runs.

## Related options

```
CARLo_GAUSS (see "CARLO_GAUSS" on page 975), sIGtail (see "SIGTAIL=VAL" on
page 982), STATIStICAL (see "STATISTICAL=0| 1" on page 982), display_CARLO (see
"DISPLAY_CARLO" on page 999), EXTMKSA (see "EXTMKSA" on page 1000), DUMP_MCINFO
(see "DUMP_MCINFO" on page 999)
```


## Tolerance Setting Using DEV, DEVX or LOT

The size of the tolerance appears in a .model command after the parameter keyword and value. The tolerance may be specified either as a percentage or an absolute quantity. To denote a percentage, the $\%$ sign must be used. Parametric expressions are allowed when specifying DEV or Lot.

The dev tolerance parameter causes devices which use the same .model statement to vary independently of each other, as illustrated in the following example:

```
c1 4 0 cmod 10p
c2 6 8 cmod 10p
.model cmod cap dev=10%
```

In the above example, both $\mathbf{c 1}$ and $\mathbf{c} 2$ use the model cmod. Their nominal values are both 10 pF . The dev declaration placed immediately after the cap keyword indicates that during a Monte Carlo analysis, their values may vary independently of each other by at most $\pm 10 \%$. So, c1 could have a value of 9.9 pF while $\mathrm{c}^{2}$ has the value of 10.1 pF during a simulation run.

In order to use a Gaussian distribution, the DEV parameter is changed to DEV/GAUSS. Using the same example, changing the distribution to Gaussian would alter the .MODEL card as follows:

```
c1 4 0 cmod 10p
c2 6 8 cmod 10p
.model cmod cap dev/gauss=10%
```

Both c1 and c2 may vary independently of each other with a Gaussian distribution, where the standard deviation is 10 percent of the nominal value, 10 pF .

The dev tolerance is appropriate for situations where the variation of parameters is uncorrelated. The devices on a printed circuit board are such an example.

The devx specification forces Eldo to use a new random value for each instance of a subcircuit. The difference with DEv is that even if a parameter is used several times in the same subcircuit, only one value will be used for that particular instance.

Note
devx can only be used in a . PARAM statement and not in a .model statement. It is impossible to have DEV and DEVX specified on the same parameter. If DEV and DEVX are specified on the same parameter, the last specification will be retained.

The lot tolerance setting causes devices which use the same .model statement to vary with each other, as illustrated in the following example:

```
c1 4 0 cmod 10p
c2 6 8 cmod 10p
.model cmod cap lot=10%
```

This is the same as the previous example with the exception that the tolerance has been changed from dev to lot. Now c1 and c2 will always have the same value. They may be both equal to 9.9 pF during one run and 10.1 pF during another run, but c 1 will not have a value of 9.9 pF while c 2 has the value of 10.1 pF during the same run.

The lot tolerance is appropriate for situations where there is a variation of the parameters track. Devices in an integrated circuit are such examples.

## Multiple Runs

It is necessary to specify the number of simulations to be run in the implementation of a Monte Carlo test. The computation time increases linearly with this number of simulations. The number of runs are specified in one of the parameters of the .MC command. Multiple runs of the selected analysis are carried out whereby the first one uses nominal component values, with subsequent runs varying model parameters according to the specifications given via the Lот and dev tolerances on each .model parameter.

## Examples

```
.model rmod res dev=2%
.mc 5 v(n5)
.tran 1n 100n
.plot tran v(n5)
```

Specifies five Monte Carlo runs of the transient analysis at the output node n5. All devices with the model name rmod have a dev tolerance attached to their nominal value.

```
.model cmod cap lot/gauss=2%
mc 5 v(n5)
.tran 1n 50n
.plot tran v(n5)
```

Specifies five Monte Carlo runs of the transient analysis at the output node n5. All devices with the model name cmod have a lot tolerance with a Gaussian distribution, where the standard deviation is two percent of the nominal value.

```
*MODEL definition
.model mod1 nmos niv=6 eox=25.0n mu0=600
+ nb=2.0e+16 kl=2.24u lot=0.5% gw=3.91u
+ gl=0.7u dev=0.07e-6 rec=0.15u vt0=0.55
.mc 7 vdb(n6)
.ac dec 10 1.0e3 1.0e9
.plot ac vdb(n6) vp(n6)
```

Specifies seven Monte Carlo runs of the AC analysis at the output node $n 6$. All devices with the model name modi have a lot tolerance attached to the parameter $\mathbf{k l}$ and a dev tolerance attached to the parameter gl.

1 An example of this type of analysis can also be found in "Tutorial \#7-Non-inverting Amplifier" on page 1363.

```
*MODEL definition
.model mod1 nmos niv=6 eox=25.0n mu0=600
+ nb=2.0e+16 kl=2.24u gw=3.91u
+ gl=0.7u rec=0.15u vt0=0.55
.mcmod mod1 kl lot=0.5% gl dev=0.07e-6
.mc 7 vdb(n6)
```

Specifies the same Monte Carlo run as the previous example, but using the .mcmod command.

## (i) For more information, see ".MCMOD" on page 715.

DEV variation specified with .MODEL statements (or .MCMOD) can refer to dimensions of the current object directly, without any need to encapsulate models into subcircuits, for example E(*, <instance_parameter_name>).

```
.MODEL M nmos VTH=1 DEV={sqrt(E(*,l)*(E(*,W))*1.0e-5}
M1 p1 p2 p3 p4 m w=10u l = 3u
```

The two lines above are equivalent to the five below:

```
.SUBCKT foo d g s b param: w=1u l=1u
.model m nmos VTH=1 DEV={sqrt(l*w)*1.0e-5}
M1 d g s b m w=w l=l
.ENDS
X1 p1 p2 p3 p4 foo w=10u l=3u
```

A full example to illustrate this is shown below:

```
* test DEVX
M1 D1 G1 0 B mos1 w=w l=l as=0 ad=0 ps=0 pd=0 m=1
M2 D2 G2 0 B mos1 w=w l=l as=0 ad=0 ps=0 pd=0 m=1
.MODEL mos1 nmos
+ level=53 version=3.24
+ u0=300 tox=5n
+ vth0=1 DEV={sqrt (E(*,l)*(E(*,w)))*1.0e-05}
.param l=5e-6 w=10e-6
.op
.MC 10
.option display_carlo EXTMKSA
```

At the end of a Monte Carlo simulation, Eldo prints in the .chi file statistical information for each .extract command. The example below shows the .chi file entry for a Monte Carlo analysis with the following .EXTRACT command:

```
.EXTRACT ac label=fc3db xycond(XAXIS, vdb(s)=yval(vdb(s),1.0e3)-3)
Distribution of FC3DB
```

```
Range [ 8.7876E+04 1.2188E+06]
Nominal value: 8.5830E+04
Average value: 5.3650E+05
Standard Deviation: 3.9332E+05
Standard Deviation based on nominal run: 6.5967E+05
```

Two standard deviation results are provided: "standard deviation" is the RMS value of the deviation of output with respect to the average value; "standard deviation based on nominal run" is the RMS value of the deviation of output with respect to the nominal run.
The example below shows how sigbin can be specified to truncate the histogram to a certain number of sigmas.

```
* analyze main distribution when there are atypical values
v1 1 0 val
.param val=1 dev/trimodal=0.00002
.distrib trimodal
+ (-1 0) (-0.999 0.1) (-0.998 0)
+(-0.1 0) ( 0 1 ) ( 0.1 0)
+(0.998 0) ( 0.999 0.1) ( 1 0)
.extract dc label=v1 v(1)
.extract dc label=v1_norm '(v(1)-1.0)*1'
.dc
*
.mc 2000 print_extract=all sigbin=4
.end
```

Specifying sigbin a value of 4 means atypical values are ignored for computing the min/max for the histogram. Eldo will gather all the samples above "mean + SIGBIN $\times$ sigma" in the Above bin, and all the samples below "mean-SIGBIN $\times$ sigma" in the Below bin.

## .MCMOD

## LOT \& DEV Variation Specification on Model Parameters (Monte Carlo)

```
.MCMOD MNAME [(list_of_instances)] PAR LOT|DEV=VAL {PAR LOT|DEV=VAL}
.MCMOD MNAME PAR LOTGROUP=my_lot_group
```

This command is used to specify the amount of variation on a given model parameter using the LOT and/or DEv parameters. By specifying the variation in this way, no modification of the .model definition concerned is required. This command is used in combination with Monte Carlo and Worst Case analyses.

## Note

If you specify a Lot/Dev variation in a .mсмод file, the variation will be around whatever value is input for that model. This may seem obvious but the point here is that the worst case models might be used and the Monte Carlo analysis be run around that. Engineers not clear on "models" might do this without realizing.

Different entities are able to share the same distribution. Anywhere Eldo accepts LOt/DEv specifications, you can specify LOTGROUP=group_name.
.MCMOD expects the name of a .MODEL command as the first argument. However, when binning models are used, there are usually several models with the same prefix (.model mymod.1..., .MODEL MYMOD. $2 .$. ) and none matching exactly the name specified in the .mCMOD command (.MCMOD MYMOD). Consequently, .MCMOD accepts only the prefix name as the argument.

If a parameter is not a primitive, but depends on parameters with no LOT/DEV specification, then a LOT /DEV specification can be set on that parameter.

## Parameters

- MNAME

Model name.

- Par

Parameter to be varied by LOT, dev or Lotgroup.

- VAL

Value of PAR Lot|DEv.

- list_of_instances

List of instances; the subsequent parameter list and variation will only apply to the specified devices. The list should be separated by spaces, and enclosed in brackets, for example:

```
.mcmod mod1 (m1 m2 m3) vt0=...
```

- LOTGROUP=my_lot_group

Specifies a "lotgroup" to enable different entities to share the same distribution. Anywhere Eldo accepts LOT/DEV specifications, you can specify LOTGROUP=my_lot_group.

Please refer to ".LOTGROUP" on page 701 for more information.

## Examples

```
*MODEL definition1
.model mod1 nmos niv=6 eox=25.0n mu0=600
+ nb=2.0e+16 kl=2.24u gw=3.91u
+ gl=0.7u rec=0.15u vt0=0.55
.mcmod mod1 kl lot=0.5% gl dev=0.07e-6
.mc 7 vdb(n6)
*MODEL definition2
.model mod1 nmos niv=6 eox=25.0n mu0=600
+ nb=2.0e+16 kl=2.24u lot=0.5% gw=3.91u
+ gl=0.7u dev=0.07e-6 rec=0.15u vt0=0.55
.mc 7 vdb(n6)
```

The above two netlist samples produce the same results.

```
.MODEL R R rho=25
.MCMOD R rho=20%
.MCMOD R r=20%
```

The example above shows the limitation of the command for $\mathrm{R}, \mathrm{L}$, and C models. The 2nd line is not valid and an error message is issued. The 3 rd line is a valid command, parameter name is $R$.

```
.MODEL NMOS.1 VTO=... WMIN=1u WMAX=10u LMIN=1u LMAX=10U
.MODEL NMOS.2 VT0=... WMIN=11u WMAX=100u LMIN=1u
+ LMAX=10U
M1 ... NMOS W=9U l=9u
M2 ... NMOS W=50u l=9u
.MCMOD NMOS VT0 lot=10%
.option modwl
.end
```

In the above example, model nmos. 1 will be attached to m1, model nmos. 2 will be attached to m2. The . мсmod command will apply to both nmos. 1 and nmos.2, that is, the same random number will be used for nmos. 1 and nmos.2.

```
.param p1 = 1
.param p2 = p1 lot = 5%
.param p3 = p2 dev = 5%
```

In the above example, MC variation on parameter p 2 is accepted, MC variation on parameter $p 3$ is ignored because its value depends on the value of parameter $p 2$. The nominal value of $p 3$ will be p 2 .

## .MEAS

## Measure Waveform Characteristics

| . MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name |  |
| :---: | :---: | :---: | :---: | :---: |
| + TRIG trig_spec TARG targ_spec |  |  |  |  |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | WHEN when_spec AT val |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | FIND wave WHEN when_spec |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | FIND wave AT val |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | FIND W('wave') |
| + WHEN when_spec [FROM=val] [TO=val] |  |  |  |  |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | DERIVATIVE wave |
| + WHEN when_spec |  |  |  |  |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | DERIVATIVE wave AT val |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | meas_k wave |
| + [FROM=val] [TO=val] |  |  |  |  |
| .MEAS [ANALYSIS_INFO] | [VECT] | [CATVECT] | label_name | PARAM='expression' |

This command can be used as an alternative to the . $\operatorname{extract~command.~.meas~has~the~same~}$ capabilities as .EXTRACT, however the syntax of .mEAS is occasionally preferred by some users. .meas can be used in three ways:

- Measuring a time interval or wave values

Measurement starts when the trig conditions, as defined by the trig_spec parameters, are matched.

- Measurement on a wave
- Combination of measurements

For compatibility with other simulators, no asterisk * character is printed in the ASCII output (.chi) file before the .meas result.

As a comparison between .meas and .EXTRACT: .EXTRACT offers greater flexibility, however it requires that each entity appearing in a .EXTRACT must be saved in memory. .mEAS does not make this requirement.

The results are listed to the ASCII output (.chi) file. By default, measurement results are saved inside the EXT folder in the main . $w d b$ file which can be read by EZwave. The command also creates a .meas. $w d b$ file with the measurement results when option measfile is specified in the netlist. If using the .cou format, the command also creates a .meas file when option measfile is specified in the netlist. The .meas or .meas.wdb file will not always be created as it depends on the type of simulation and the specification of the .meas command.

## Parameters

- ANALYSIS_INFO
should be replaced with one of the following parameters;
AC
Measurement during AC analysis.

```
DC
    Measurement during DC analysis.
DCTRAN
    Measurement after the DC analysis performed prior to a TRAN analysis.
DCAC
    Measurement after the DC analysis performed prior to an AC analysis.
DCSWEEP
    DCSWEEP measurement.
TRAN
    Measurement during TRAN analysis.
NOISETRAN
    Measurement during NOISETRAN analysis.
```

- VECT

By default, .meas returns the first value which matches the expression. But if keyword vect is set on the .meas statement, then all values will be returned.

- catvect

Works in the same way as vect but in addition all measurements corresponding to all analyses (. STEP/ . TEMP) will be combined. This functionality is usually used in conjunction with the contour function in the .PLOT command.

1 For more information on the contour function, see "CONTOUR" on page 798.

- label_name

Identifies the .meas command in all output files. label_name must be defined.

- trig

Measurement starts when the trig conditions, as defined by the trig_spec parameters below, are matched:

- trig_spec:

WAVE VAL=val [TD=val] [CROSS=index|LAST] [RISE=index|LAST]

+ [FALL=index|LAST] [SIG_H=val] [SIG_L=val]
or:
AT [=]val
WAVE
Name of wave.
VAL
Threshold value.
TD
Time delay until measurement commences.


## CROSS

Number of times the threshold must be crossed (in whichever direction) before measurement starts. Keyword LAST can be specified in place of a value.

## RISE

Number of times the wave values rise above the threshold before measurement starts. Keyword LAST can be specified in place of a value.

FALL
Number of times the wave values fall below the threshold before measurement starts. Keyword LAST can be specified in place of a value.

SIG_H, SIG_L
High and Low signal values respectively. Default high and low values are taken from the threshold value vas. These high and low values are used to validate a transition before incrementing the cross, rise or fall counter.

- at

Measurement starts/stops at val. The val depends on the analysis type: time for TRAN analysis, frequency for AC analysis, or the parameter (x-axis value) for DC analysis.

- targ

Measurement stops when the targ conditions, as defined by the targ_spec parameters, are matched.

- targ_spec

The arguments are the same as for trig_spec. If the time delay $\boldsymbol{T D}$ is not specified, the time delay specified in trig_spec will be used.

## - when

Measurement stops when the when conditions, as defined by the when_spec parameters, are matched.

- when_spec

The arguments are the same as for targ_spec, except that both WAVE and VAL specifications are replaced by either of the following:

```
WAVE=VAL
WAVE1=WAVE2
```

- derivative

Keyword which can be used in place of FIND, to specify that it is the derivative of the wave that must be returned when when specification is matched.

- meas_k

Used for measurement on a wave. This can be one of the following keywords:
AVG
Average value of the waveform in the range [ $F R O M, T O$ ].

RMS
RMS value of the waveform in the range [FROM, TO].
MIN
Minimum value of the waveform in the range [FROM, TO].
MAX
Maximum value of the waveform in the range [FROM, TO].
PP
Peak-to-Peak value of the waveform in the range [FROM, TO].

- PARAM='expression'

Regular expression that combines the label names of the .MEAS commands. expression cannot be a wave name. Plot quantities such as i(), v(), lv9() are only accepted in a .meas dC analysis. For example:

```
.MEAS DC vth0 param='lv9(m)'
```


## Examples

The example below will return the last time that $\mathbf{v}$ (in1) crossed value 2.0 while falling:
. MEAS TRAN mymo TRIG AT=0 TARG v(in1) val=2 FALL=LAST
The example below will return the value of $\mathrm{v}(1)$ when $\mathrm{v}(2)$ becomes equal to the $\mathrm{v}(5)$ measurement, starting after a delay of $3 n$ :

```
.MEAS TRAN foo FIND v(1) WHEN v(2)=v(5) TD=3n
```

The example below will return the average of $\mathrm{v}(\mathrm{in} 1)$ between 3 n and 5 n :
. MEAS TRAN my_avg avg AVG v(in1) FROM=3n TO=5n
The example below will return the average of $\mathrm{v}(\mathrm{s})$ :

```
.PARAM p1=1
.MEAS TRAN avg_name AVG V(s)
```

The example below will return the value of measurement named avg_name + value of parameter P1:
. MEAS TRAN f2 PARAM='avg_name+p1'
The following example shows how the vect keyword can be used to return all the values which match the expression. By default, . MEAS returns the first value which matches the expression.

```
v1 1 0 pulse(0 5 0 1n 1n 8n 20n)
r1 1 0 1
.extract vect xup(v(1),2.5)
.meas vect tran memes trig at 0 targ v(1) val=2.5 rise=1
.tran 1n 100n
.end
```

The following example shows how the w notation can be used with the .meas command. This will search the value of wave $\mathrm{vp}(1)$ when wave $\mathrm{vdb}(1)$ will cross zero between 10 Hz and 1000 Hz .

```
.MEAS AC ph1 FIND W('vp(1)') WHEN vdb(1)=0 FROM=10 TO=1000
```


## Related option

FROM_TO (see "FROM_TO=0|1" on page 964)

## .MODDUP

## Aspire/SimPilot Command

```
.MODDUP device_name [... device_name]
.MODDUP element_name
```

This command is useful in connection with SimPilot/Aspire only. It tells Eldo that for each device_name a private . MODEL command be created. Then, it will be possible for the SimPilot/Aspire engine to alter the content of this new model command via commands.

When the netlist is sourced, SimPilot/Aspire stores the .moddup arguments (device instance names) and relates these to the associated .model commands. Therefore, the user does not need to manually duplicate .model commands inside the netlist. These copies reside inside the Eldo simulator.

With element_name specified, the effect of this command is that the model attached to element_name is duplicated, and becomes private to that element. Parameters of the associated . MODEL command can be modified/displayed in interactive mode via the commands:

```
SET EM(Element_name,Model_parameter) = value
```

PRINT EM(Element_name, Model_parameter)

- device_name

Device instance name.

- element_name

Element name.
.MODDUP 'carries' parameter dependencies, for example:

```
.PARAM P1 = 1.0
.MODEL FOO NMOS VTO = P1
M1 .... FOO ..
M2 .... FOO ..
.MODDUP M1
.STEP PARAM P1 1 2 1
.END
```

Here, . STEP P1 will update the vto parameter of FOO as well as updating the vT0 parameter of the newly created model attached to m1.
(1)

For an example, please see Example-device mismatch for Eldo v4.4.1 or later of the Aspire User's Manual.

## .MODEL

## Device Model Description

```
.MODEL MNAME TYPE NONOISE [PAR=VAL]
.MODEL LIB FILENAME MODNAME [LIBTYPE]
```

This command groups sets of pre-defined parameters which may be used by one or more devices. Models may be described directly in the input file or may be read from a library file using either the second syntax above or the . Lid and .addilb commands. The second syntax allows no continuation lines.

It is also possible to specify model parameters on the instance command. The effect is that a private model will be created for that instance.

By default, when Eldo encounters multiple definitions of .MODEL statements an error is reported and the simulation is stopped. Specify option USEFIRSTDEF to force Eldo to only use the first definition (any further definitions are ignored) to allow the simulation to proceed.

## Parameters

- MNAME

The model name. It must not start with a number.

- type

Defines the model used. The following models are available:

## Table 10-16. Model Types

| RES | Resistor |
| :--- | :--- |
| R | RC wire |
| CAP | Capacitor |
| IND | Inductor |
| NPN | NPN bipolar junction transistor |
| PNP | PNP bipolar junction transistor |
| LPNP | Lateral PNP bipolar junction transistor |
| D | Diode |
| NMOS | N-channel metal oxide field effect transistor |
| PMOS | P-channel metal oxide field effect transistor |
| NJF | N-channel junction field effect transistor |
| PJF | P-channel junction field effect transistor |
| NSW | N-type switch (SC) |

## Table 10-16. Model Types

| PSW | P-type switch (SC) |
| :--- | :--- |
| OPA | Operational amplifier (SC) |
| MODFAS | Analog macromodel (including LDTL Lossy Transmission Line) |
| SP | Sampled Matrix model (Lossy Transmission Line) |
| U | U model (Lossy Transmission Line) |
| w | RLGC model (Lossy Transmission Line) |
| LOGIC | Digital Gate |
| A2D | Analog-to-Digital converter |
| D2A | Digital-to-Analog converter |
| MACRO | Macromodel (including S parameter block) |

- LIB

Keyword indicating a model library file is to be used.

- FILENAME

Name of the library file that contains the model description.

- MODNAME

Name of the model stored in library file filename. See the "Library variant management" on page 694 in the . LIb command description for details.

- NONOISE

Specifies that no noise model will be used for the corresponding object when performing noise analysis. Therefore, the object presents no noise contribution to the noise analysis. This can be overwritten on an instance specification using NOISE=1.

- $\quad$ PAR=VAL

Name and value of a model parameter. Model parameters not given values are assigned default values. Model parameters may also be declared via the .PARAM command. See the ".PARAM" on page 778 for further details.

The parameter BULK=node_name can be specified on a .MODEL NMOS|PMOS command. This will connect the bulk node to node_name if it is not specified in the instantiation of the model. By default node_name is 0 .

- LIBTYPE

Name of a library variant to be used.
For more information on electrical parameters of models, refer to the Device Models chapter.

## Related option

```
USEFIRSTDEF (see "USEFIRSTDEF" on page 962)
```


## Examples

```
*MODEL definition
.model rmodel res tc1=0.001 tc2=0.005
...
*main circuit
r2 n1 n19 rmodel 2.5k
```

Specifies the resistor r2 of model type rmodel.

```
*BJT model definition
.model qmod npn bf=160 rb=100 cjs=2p
+ tf=0.3n tr=6n cje=3p cjc=2p vaf=100
*main circuit
q23 10 24 13 qmod
```

Specifies the bipolar transistor q23 of model type qmod.

```
*OPAMP model definition
.model ampop modfas voff=100e-6
*main circuit
yopa1 opamp1 n2 n1 n3 0 model: ampop
```

Specifies the single-stage 1-pole op-amp yopa1 with the electrical parameters specified in the model ampop.

```
*NOR# .MODEL definition
.model nor_1 logic vhi=5 vlo=-5 vth=0
+ tpd=2.5n cin=0.5p
...
*main circuit
nor#_1 n1 n2 n3 n4 o1 nor_1
```

Specifies a NOR gate nor\#_1 with four input nodes n1, n2, n3 and n4 and an output node ०1, the parameters of which are described in the model nor_1.

```
M1 ... MOD1 w=1u l=1u M(DW)=0.5u
M2 ... MOD1 w=1u l=1u
.model MOD1 NMOS DW=3u LOT=3%
```

In this example, a private model will be created for m1. Changing the DW parameter value of model MOD1 (via .STEP for instance) will not affect the value of parameter Dw for the model attached to device m1.

## Note

This feature only works for MOS, BJT, Diodes and JFET. Care must be taken when using this feature, since a private model is created for each instance. The memory requirement on circuits that contain many such model parameter specifications on instance commands can be very high. Monte Carlo specifications are not propagated to the new model. In the example above, the DW value of instance m1 will not be changed during a Monte Carlo analysis.

In the following example the bulk node will be connected to node 4 . This is because a node has not been specified in the instantiation of the MOS model and the parameter BULK has been specified in the .model command.

M1 123 N W=10u $1=3 \mathrm{U}$
.MODEL N NMOS BULK $=4$
If Bulk was omitted, by default the bulk node would be connected to node 0 (ground node).

```
.model res r r=2 NONOISE
r1 1 2 res 1k noise = 1
r2 2 3 res 1k
```

This example shows use of the nonoise parameter. In this example, device r1 will generate noise, not r 2 .

## Monte Carlo and Models

The Monte Carlo command is used in combination with extra parameters placed in the .model command. Each .mODel parameter to be subjected to statistical variation, may have two extra related parameters added, DEV and цот. The significance of these parameters is explained in the following paragraphs.

An example of a .model command, modified to include Monte Carlo analysis parameters, is shown below:

```
.model mmod nmos vto=0.65v dev=0.4v
+ tox=1.5e-7 dev=0.2e-7 lot=5%
```

The first dev declaration refers to the vto parameter, and the second (combined) dev \& lot declaration refers to the tox parameter.

## .MODLOGIC

## Digital Model Definition

Caution $\qquad$
Kept for compatibility reasons only and should no longer be used.

For the new syntax, see "Digital Model Definition" on page 449.

```
.MODLOGIC MNAME [VHI=VAL1] [VLO=VAL2] [VTH=VAL3] [VTHI=VAL4]
+ [VTLO=VAL5] [TPD=VAL6] [TPDUP=VAL7] [TPDOWN=VAL8]
+ [CIN=VAL9] [DRVL=VAL10] [DRVH=VAL11]
```

Used for the definition of digital gate models.

## Parameters

For detailed information on the parameters, see "Digital Model Definition" on page 449.

## .MONITOR

## Monitor Simulation Steps

.MONITOR ANALYSIS [=] [modulo]
This command can be used to display the steps taken by the simulator when doing an AC, TRAN or DCSWEEP simulation. Current TIME/FREQ or DCSWEEP value is also displayed. This command can be used for debugging purposes, that is, to see how the simulation proceeds.

Eldo will display the current time and time step every modulo steps.

## Parameters

- ANALYSIS

Analysis type for which you request simulation steps to be monitored. Can be one of the following:

DC Specifies that a DC analysis is monitored.

AC
Specifies that a AC analysis is monitored.
TRAN
Specifies that a transient analysis is monitored.

- modulo

Number of steps at which the information is displayed. Default is zero, meaning all values are printed out.

## Examples

.MONITOR AC
Eldo will display all the frequency points in an AC analysis.

## .MPRUN

## Multi-Processor Simulation

```
.MPRUN [ALL|HOST={host[(nbjobs)]}|FILE=filename}] [NBLICENSES=val]
[MAX_NBJOBS=val] [CLEAN=YES|NO] [QUEUE=YES|NO] [SETENV=YES|NO]
+ [VIEW_COMMAND=YES NO] [CHECK_DELAY=val] [INIT_FILE=filename]
+ [DEFAULT_INIT=YES NO] [NETWORK_DIR=directory]
+ [CD_WORKDIR=YES|NO] [LOGFILE=YES|NO]
+ [USE_LOCAL_HOST=YES|NO] [FLAT=YES|NO]
[FILE_PREFIX=(name1, name2,..., nameX)]
[USE_SSH=YES|NO] [SSH_OPTIONS="{<options>}"]
[CHECK_ALL_HOSTS=YES|NO]
+ [SYNCHRO_NOMINAL_MC=YES|NO]
.MPRUN DISPATCHER ...
```

See ".MPRUN and external dispatchers" on page 734 for .MPRUN DISPATCHER syntax.

This command is used to run multiple simulations on one multi-processor machine, or on many machines. .ALTER, .MC, .TEMP, .STEP, .DATA and . OPtIMIze are distributed by this command. It can also be used with data sweeps on .AC and .TRAN commands.

| Note |
| :--- |
| Eldo is also capable of multi-threading simulations to speed-up simulation. See "Multi- <br> Threading Eldo Simulations" on page 58 for information. |

This command uses a client/server architecture to ensure maximum efficiency. Once remote jobs have been submitted, the localhost may or may not start a simulation depending on the USE_LOCAL_HOST option. In both cases it has the responsibility to merge individual runs, unless the flat method is enabled. The message "Collecting results" is printed when the main job is waiting for results of a run.

Both main and remote jobs are not restricted to some runs. A side effect for very small simulations is that the localhost (with USE_LOCAL_HOST=YES) may perform all runs before remote jobs have established connections.

The child processes are by default launched through an $r$ sh call which inherits the environment variables used in . INClude or . LIb statements. Temporary results are stored in subdirectories named <NETLIST_NAME>.part $\langle X\rangle$ where $X$ is an incrementing counter. By default—and unless they are in use-temporary directories are removed once the simulation is complete.

Child processes can be submitted either by $r s h$, $s s h$, or by an external dispatcher. These specifications are exclusive.

## Notes

1. In all cases, Eldo will warn you if a host cannot be used. This will happen when:

- You do not have the permissions to see the machine and/or to write in the working directory. This error must be fixed by the system administrator before the .MPRUN command can be used.

2. The netlist must be in a shared directory (a place visible from the other machines on the network).
3. If using local installations of Eldo, the installation patches (not the binaries) must be strictly identical on all machines.
4. Users need to be able to rlogin to other machines without supplying password.

If a user needs a password to perform an rlogin to other servers, when Eldo attempts to rlogin to other systems to launch tasks it will fail because the other machines require passwords and Eldo cannot supply them.
5. The result of a .CALL_TCL command used with .MPRUN is unpredictable since the behavior of the Tcl function is unknown to Eldo. It does not know if the command opens output files or returns a waveform.
6. .MPRUN cannot be specified inside a .ALTER section.

## Parameters

## Note



All boolean keywords, that is, CLEAN, SETENV, queue, view_COMMAND, CD_WORKDIR,
logrile can be set using: <keyword> [=yes|no|1|0]. For example, specifying the setenv keyword is equivalent to setenv=yes, which is equivalent to setenv=1. Additionally, when the setenv keyword is not specified it will use its default value, in this case it would be Setenv=no, which is equivalent to Setenv=0.

## - ALL

This is the default. This keyword specifies Eldo to run the simulation on all the processors of the machine. Eldo will find the number of processors of the machine and distribute the tasks between them. If the machine has one processor, Eldo will run the simulation normally without taking this command into consideration.

- HOST=\{host1[(nbproc1)] host2[(nbproc2)]... hostN[(nbprocN)]\}

Specifies Eldo to run the simulation on the list of machines: host1, host2, ... hostN (commas are optional). Eldo will distribute the tasks on the list of machines specified. nbjobs is an optional parameter that explicitly tells Eldo the maximum number of jobs that can be submitted on this machine. On multi-processor stations, this number should be the number of processors.

- FILE=filename

Specifies the name of a file which contains a list of machine names (with a number of processors if needed). The file can have any extension or no extension at all. The first line of the file is read. Example file contents:

```
pluton kebra(3)
morkai(2) nao
cochise
```

- nblicenses=val

Specifies the maximum number of licenses that this job can use. It must be greater than 1 to be taken into account, since the parent process always takes its own license.

- MAX_NBJOBS=val

Specifies the maximum number of jobs that can be submitted for all machines.

- Clean [=YeS $\mid$ No]

Default value is YES. This specifies Eldo to remove temporary files created in any child process subdirectories, together with removing the subdirectories themselves. If keyword is set to NO, the temporary files are not removed.

- Queue [=Yes $\mid$ No]

Instructs the system to wait for the release of a license if one is not immediately available. A consequence is that the parent process will hang until its child process has finished. Default value is NO.

- SETENV [=YES $\mid \mathrm{NO}]$

Keyword specifies Eldo to reuse all environment variables in child processes, and not only these given on . LIb and/or . Include statements. Default value is NO.

- VIEW_COMMAND [=YES $\mid$ NO]

Prints the command Eldo submits to the remote host and the contents of the command file. Default value is NO.

- CHECK_DELAY=val

Forces Eldo to wait val seconds while checking host connections. This is useful when using both Linux and Unix networks, since a delay can appear between the time when a remote command is executed on Unix and the time when the result of the command is effective on Linux.

- INIT_FILE=filename

This allows you to define a script file which is sourced before running child processes.

- DEFAULT_INIT [=YES $\mid$ NO]

Default value is YES. If keyword is set to NO, it tells Eldo that the script specified in init_file will replace any other default. This should always be used in conjunction with INIT_FILE=filename. If using this, it is your responsibility to ensure that the script file correctly sets the path and required variables for Eldo to run.

- NETWORK_DIR=directory

Specifies the network name of the directory where the netlist is located.

- CD_WORKDIR[=YES|NO]

Forces Eldo to change the working directory in the remote environment to the directory where the netlist is located. Default value is YES.

- LOGFILE [=YES |NO]

This controls the redirection of the standard output of sub-processes. The default value is YES, which means that Eldo dumps the standard output in <NETLIST_NAME>.log in the temporary directories.

- USE_LOCAL_HOST [=YES | NO]

Setting this option to NO tells Eldo that it cannot use the local host to perform some simulations. Default value is YES (the local host is the machine on which the main process has been launched).

- FILE_PREFIX=(name1, name2, . . , nameX)

In the case of splitting .ALTER statements, you may want to rename the output files of each run. If a flag is given after . ALTER, it is used as the name. Output names can also be redefined with this file_Prefix option. For example if a netlist contains two .alter statements and the .MPRUN option FILE_PREFIX=(first, second, third), output files for each run will be:

- for the netlist before .ALTER statements: first.chi, first.wdb, and so on
- for the netlist after the first .alter statement: second.chi, second.wdb
- for the netlist after the second .ALTER statement: third.chi, third.wdb
- FLAT [=YES $\mid$ NO]

The usual .MPrun mechanism uses temporary directories to store the results of intermediate runs. In the case of splitting . ALTER statements, if this option is set to YES, Eldo will use different names for each intermediate run instead of using directories. .ALTER sections are submitted as if they are independent netlists. It is recommended to use this option in conjunction with file_prefix to define the names of the runs. Default value is NO, and it is ignored if no . ALTER statements are declared.

- USE_SSH[=YES|NO] [SSH_OPTIONS="\{<options>\}"]

Setting the USE_SSH option to YES tells Eldo to work with ssh (secure shell) instead of $r s h$ (remote shell). Default value is NO (remote shell). Secure shell options can be specified with the SSh_OPtions parameter.

- CHECK_ALL_HOSTS [=YES|NO]

If YES, Eldo will check that all hosts are valid and report warning or error messages depending on the host status. Default value is NO, which means the connection to all hosts specified with the HOST argument is not checked. In addition:

If USE_LOCAL_HOST=YES, none are checked.
If uSE_LOCAL_hOSt=NO, Eldo just checks that at least one connection is active. It reduces the overhead before starting the mprun simulation.

- SyNCHRO_NOMINAL_MC[=YES|NO]

If YES, the .MPRUN mechanism will impose synchronization points at each nominal Monte Carlo run in order to provide the same DC solution to all remote processes. Default value is NO.

During a Monte Carlo analysis, the DC solution of the first run is taken as a reference to speed-up convergence of the following runs. When .MPRUN is used, the first run performed by each individual process is not the same. This means the reference DC solution is not uniform over all processes. The visible effect may be very small variations on waveforms and extracts (numerical noise).

If the design contains several levels of multi-run commands, including a .mC, the .MPRUN can significantly slow because all processes will have to wait until the nominal run is finished.

## Usage

Before performing a run on a remote host, the .MPRUN command must initialize the remote environment. By default, Eldo does the following before running a simulation:

```
cd <working_directory>
setenv MGC_AMS_HOME ...
setenv LM_LICENSE_FILE ...
```

If you specify init_file=<filename>, the sequence becomes:

```
cd <working_directory>
source <filename>
setenv MGC_AMS_HOME ...
setenv LM_LICENSE_FILE ...
```

and if you also specify default_init=no, the sequence becomes:

```
cd <working_directory>
source <filename>
```

and if you also specify CD_WORKDIR=NO, the sequence becomes:

```
source <filename>
```

and if you remove the INIT_FILE=<filename>, absolutely no initializations will be performed before Eldo is run.

## Examples

```
.MPRUN HOST=host1, host2 NBLICENSES=2 QUEUE=YES
```

Specifies Eldo to run the simulation on both the host1 and host2 machines. A maximum of two licenses can be used by this simulation. If a license is not immediately available, the system will wait for the release of a license.

```
.MPRUN HOST=host3(2) host4
+ INIT_FILE=script.shell DEFAULT_INIT=NO
```

Specifies Eldo to run the simulation on both the host3 and host4 machines, also with two processors of host 3 specified as running the simulation. A script file script.shell will be sourced before running child processes. This script will replace any other default initialization file.

An example standard output of an .MPRUN job is as follows:

```
.TEMP -10 10
.MPRUN
Memory space allocated (bytes): 3603249
22 elements
1 6 \text { nodes}
3 input signals
(localhost) - No limitation applied: a maximum of 1 job(s) will be
submitted.
(localhost) - Job Id 0 submitted to host SHAMBHALA
(localhost) - Standard output of localhost redirected to file:
                                    test02.main.log
(localhost) - Starting run 1.
(localhost) - Completed run 1 of 2
(localhost) - Collecting results of run 2
(shambhala - 0) - Starting run 2.
(shambhala - 0) - Completed run 2 of 2
***>GLOBAL CPU TIME 0s 220ms <***
***>GLOBAL ELAPSED TIME 6s <***
```


## .MPRUN and external dispatchers

```
.MPRUN DISPATCHER= [LSF |
+ (dispatcher_name, install_check_cmd, submission_cmd]
+ [REMOVE_QUOTE=YES|NO] [DISPATCHER_OPTIONS=options]
+ [NBLICENSES=val] [MAX_NBJOBS=val] [CLEAN=YES|NO]
+ [QUEUE] [SETENV] [VIEW_COMMAND] [CHECK_DELAY=val]
+ [INIT_FILE=filename [DEFAULT_INIT=YES|NO]]
+ [USE_LOCAL_HOST=YES|NO] [FLAT=YES|NO]
+ [FILE_PREFIX=(name1, name2,..., nameX)]
+ [LSF_JOB_PREFIX=lsf_prefix]
```

```
.MPRUN
```

.MPRUN

+ DISPATCHER_TEMPLATE=command_line
+ [USE_LOCAL_HOST=YES|NO] [FLAT=YES|NO]
+ [FILE_PREFIX=(name1, name2,...,nameX)]

```

A dispatcher is software which shares and manages computer resources across a network. Instead of a basic remote shell command, the dispatcher uses various criteria (memory usage, CPU charge) to determine which machine is suitable to run the simulation on. The second
syntax above is useful for . ALter dispatching only. For all other options listed above, please refer to the descriptions on the previous pages.
- DISPATCHER=LSF

Specifies Eldo to use LSF as external dispatcher. This syntax is a shortcut to
DISPATCHER=("LSF","bsub -V","bsub").
For more information on LSF, please visit the Platform web site:
http://www.platform.com
- DISPATCHER=(dispatcher_name, install_check_cmd, submission_cmd)

The general syntax to configure a dispatcher.
```

dispatcher_name

```
name of the software (required for print purpose only).
```

install_check_cmd

```
a command that can prove the software is accessible.
submission_cmd
the command that submits a job to the engine.
- REMOVE_QUOTE [=YES \(\mid\) NO]

Modifies how Eldo manages double quotes inside the DISPATCHER_OPtions argument. If defined, it is mandatory to set it before the DISPATCHER_OPtions argument. Default value for LSF is YES, and NO for other dispatchers.
- DISPATCHER_OPTIONS=options

This keyword allows to send extra options to the dispatcher submission command. The dispatcher options must be enclosed in (), \{ \}, " " or ' '. If enclosed in () or \{ \} Eldo may add some spaces between items. To keep the exact syntax, use " " or ' ' if the options contains some double quotes.
- DISPATCHER_TEMPLATE

This option allows to completely override the usual mprun mechanism. It is useful for .ALTER dispatching only. The user is in charge of providing a valid shell command which will dispatch jobs. This command can use predefined variables which are substituted by Eldo before executing the command. These variables are:

\footnotetext{
\%NETLIST_NAME \%
stands for the name of the netlist \%RUN_NAME\% stands for the name of each run (may be redefined with FILE_PREFIX)
\%RUN_NUMBER\%
stands for an absolute run counter (starting from 1) \%MPRUN_OPTIONS\% is a mandatory variable which represents internal options added by Eldo.
}
- LSF_JOB_PREFIX=lsf_prefix

Specifies prefix for dispatched job names. By default, jobs submitted to LSF are named <netlist_base_name>.part<job_id>. If this argument is specified, the submitted jobs will be named <lsf_prefix_name>.part<job_id>.

\section*{Example with LSF}
```

.MPRUN DISPATCHER=LSF

+ DISPATCHER_OPTIONS=(-q myqueue -m "host1 host2")
+ MAX_NBJOBS=5

```

Specifies Eldo to use the LSF management system as a dispatcher for the remote jobs. The simulation will be run on both the host1 and host2 machines. A maximum of five jobs will be submitted to LSF. -q myqueue is the LSF option which controls the Batch Queue to which the jobs will be submitted.

\section*{Example with .ALTER dispatching}

Suppose file mpex.cir contains the following command in conjunction with two .ALTER statements:
```

.mprun

+ flat=yes
+ use_local_host=no
+ dispatcher_template="eldo %NETLIST_NAME% -queue %MPRUN_OPTIONS% >
%RUN_NAME%.log"
+ file_prefix=(first, second, third)

```

After parsing the netlist, Eldo will immediately execute the following commands:
```

eldo mpex.cir -queue ... -out first > first.log eldo mpex.cir -queue ...
-out second > second.log eldo mpex.cir -queue ... -out third > third.log

```

This example only demonstrates the syntax since it does no actual dispatching.

\section*{.MSELECT}

\section*{Automatic Model Selection}
.MSEL[LECT] dummy [MODELS] mod1 [mod2 [mod3 [...]]]
This command allows you to select models automatically for MOS devices. The selection is based on:
- the size and temperature of the specific device (W, L, TEMP)
- the size and temperature constraints of each model in the list provided (WMIN, WMAX, LMIN, LMAX, TEMPMIN, TEMPMAX)

It is not allowed to have a model statement with the same name as an mselect dummy model name. If a model statement has the same name as an mselect dummy model name, Eldo will display an error message, for example:

ERROR 953:Dummy model name MOD1 on .MSELECT statement is also defined on a .MODEL statement

\section*{Parameters}
- dummy

Dummy model name that is used on the devices for which you want automatic model selection.
- models

Optional keyword used only to enhance .mSELECT statement readability.
- mod1 ... modn

List of model names from which a new model is selected.

\section*{Additional information}
- Device temperature can also be specified. Eldo will check against model parameters TEMPMIN/TEMPMAX to select the right device
- If a value is not specified for any of the models parameters (TEMPMIN/TEMPMAX/LMIN/LMAX/WMIN/WMAX) the checks versus the limits are not done.
- Models are searched in the order there are given on the mselect statement
- Many mselect with the same name can be defined. The previous definitions are automatically overwritten. Eldo will use the last one, for example:
```

.mselect dummy2 models mo1 mo2.
.mselect dummy2 models mo1 mo2 mo3 mo4

```

The last one will be used.
- When none of the models defined on a mselect fit with the device parameter an error message is displayed, for example:
```

ERROR 845: OBJECT "M1": None of the models in .MSELECT fits this

```
instance
- If the one the models specified on the mselect model list does not exist a simple warning is emitted, for example:

Warning 488: COMMAND .MSELECT: Model MOD7 is not defined
- When 2 different types of models (example NMOS and PMOS) an error is emitted, for example:
```

ERROR 945: Wrong Model type for MOD2 on .MSELECT statement - mixing
models type is not allowed

```

\section*{Limitation}

Eldo implementation of mselect only work for MOS devices and models.

\section*{Example}

An example with mselect is below.
```

.MODEL mod11 ...
.MODEL mod12 ...
.MODEL mod21 ...
.MODEL mod22 ...
.mselect mod2 MODELS mod21 mod22
.mselect mod1 MODELS mod11 mod12
M1 A G VDD VDD MOD2 W=120U L=5.5U
M2 B G VDD VDD MOD2 W=120U L=5.5U
M3 D K A VDD MOD2 W=116U L=3.5U
M4 S K B VDD MOD2 W=116U L=3.5U
M5 C I VSS VSS MOD1 W=63U L=6U
M6 A EP C VSS MOD1 W=130U L=4U
M7 B EN C VSS MOD1 W=130U L=4U
M8 D D FF VSS MOD1 W=5.5U L=4.5U
M9 S D E VSS MOD1 W=5.5U L=4.5U
M10 FF E VSS VSS MOD1 W=42U L=4U
M11 E E VSS VSS MOD1 W=42U L=4U
M12 G G VDD VDD MOD2 W=14.5U L=5.5U
M13 G G H VSS MOD1 W=9U L=5.5U
M14 I I H VDD MOD2 W=19U L=4.5U
M15 I I VSS VSS MOD1 W=6U L=6U
M16 J G VDD VDD MOD2 W=20U L=5.5U
M17 J J K VSS MOD1 W=26U L=3.5U
M18 NL I K VDD MOD2 W=3U L=3.5U
M19 NL NL VSS VSS MOD1 W=4U L=3.5U

```

There are two mselect statements and 4 models definitions. The MOS devices are instantiated using the mselect dummy names instead of models real names. In this example only W and L
instance parameters are used. The actual models used on the instances are selected when these dimensions are within the model parameters LMIN/LMAX and WMIN/WMAX

As the results of the selection you will have:
```

* M1, M2 M3 M4
mapped to MOD21
* M12 M14 M16 M18
* M5 M8 M9 M10 M11 M13 M15 M17 M19
* M6 M7
mapped to MOD22
mapped to MOD11
mapped to MOD12

```

\section*{.NET}

Network Analysis

\section*{2-port network}
```

    .NET output input RIN=val ROUT=val
    ```

\section*{1-port network}
```

.NET input RIN=val

```

The . NET command is another approach to extract the \(S\) parameters (Scattering parameters), the Y parameters (Admittance), the Z parameters (Impedance) or the H parameters (Hybrid) in the frequency domain for a specified circuit.

The circuit can only have one or two ports.

\section*{Parameters}
- input

Can be V source or I source.
- output

Can be V source, I source or \(\mathrm{V}(\mathrm{NP}, \mathrm{NN})\).
- RIN ROUT

Specify the values of access resistors of the input and output port.

\section*{Example}
```

.ac dec 500 1e6 10e6
.net v(outputnode) vinput_source RIN=50 ROUT=50

```

The following example shows a 1-port network extraction on voltage source v1 with input access resistance of 50 ohms.
```

v1 1 0 ac 1 0
r1 1 2 1
c1 2 0 10p
.ac dec 10 1 10G
.plot ac sdb(1,1)
.plot ac sp(1,1)
.net v1 rin=50

```

\section*{.NEWPAGE}

\section*{Control Page Layout}
. NEWPAGE
This command allows the control of the saved windows file in the EZwave waveform viewer. It allows lines to be inserted into an Eldo netlist, with the effect that . PLOT commands located between two .newpage commands will be plotted in the same EZwave window. .newpage only acts on.\(w d b\) and .cou files.

\section*{Note}
\(\qquad\)
The number of items per .-PLOT is not limited. It is possible to have any number of waves in the same plot, although reading the ASCII plot may be difficult.

See ".PLOT" on page 791 for more information.

\section*{Example}
```

.PLOT TRAN (v1) (v2)
.PLOT TRAN (v3) (v4)
.PLOT TRAN (v15)
.NEWPAGE
.PLOT TRAN (v15)
...

```

This allows the user to control page layout, Eldo will plot the graphs following the .newpage command in a new EZwave window.

\section*{.NOCOM}

\section*{Suppress Comment Lines from Output File}
. NOCOM
This command suppresses any comment lines in the ASCII output (.chi) file which come after it in the netlist. Saves disk space.

\section*{Example}
```

example title
.nocom
*This is a sample comment line
r1 1 2 5
*here is another
.end

```

\section*{.NODESET}

\section*{DC Analysis Conditions}
```

.NODESET V(NN)=VAL [SUBCKT=subckt_name] {V(NN)=VAL [SUBCKT=subckt_name]}

```

This command is used to help calculate the DC operating point by initializing selected nodes during the first DC operating point calculation. After the first calculation has been completed the node values are "released" and a second DC operating point calculation is started. This command is useful when the whereabouts of the DC operating point is known, enabling the simulator to converge directly to it and also for bistable circuits or circuits with more than one operating point.

The .nodeset command differs from the . Guess command in so far as when using . NODESET node voltages are fixed for the duration of the first DC calculation, whereas the node voltages are only initialized for the first iteration of a DC operating point calculation when using . guess. It is very important to specify realistic .nodeset values as convergence problems may occur when this command is not used properly.

\section*{Note}

By default, the first .nODESET specification has precedence over subsequent .nODESET specifications. Setting .option licn, the last .nodeset specification will have precedence.


See "LICN" on page 979 for further information.

\section*{Parameters}
- \(\quad \mathrm{V}(\mathrm{NN})=\mathrm{VAL}\)

Voltage at node nn in volts.
- SUBCKT=subckt_name

If specified it will fix the voltage of the preceding node in all instances of the subcircuit subckt_name.

\section*{Examples}
\[
\text { .nodeset } v(n 4)=6 v \quad v(n 5)=2 v \quad v(n 6)=-5 v
\]

Specifies that during the first DC operating point calculation, the initial values for the voltages at the nodes \(n 4, n 5\) and \(n 6\) be initialized to \(6 \mathrm{~V}, 2 \mathrm{~V}\) and -5 V respectively.
```

.nodeset v(2)=3v SUBCKT=sub1 v(4)=-2v SUBCKT=sub2

```

Specifies that during the first DC operating point calculation, the initial values for the voltages at node 2 of subcircuit sub1 and node 4 of subcircuit sub2 will be initialized to 3 and -2 V respectively.

\section*{.NOISE}

\section*{Noise Analysis}
.NOISE OUTV INSRC NUMS
The .nOISE command controls the noise analysis of the circuit and must be used in conjunction with an AC analysis.

The results of noise analysis runs are output using the .PRINT and .PLOT commands.
It is possible to control the output of the noise information via the noxtabnoise option, see "NOXTABNOISE" on page 1005.

\section*{Note}

NOISE analysis may also be run from within a .TRAN command, see "AC in the middle of a .TRAN" on page 543 for more details.

\section*{Parameters}
- outv

Name of the output voltage node for which the equivalent output noise is to be calculated. The syntax is as follows:
v(N1[, N2])
Specifies the voltage difference between nodes N 1 and N 2 . If N 2 and the preceding comma are omitted, ground is assumed.

\section*{I (Vxx)}

Specifies the first argument as a voltage source.
- insRc

Name of the input voltage or current source for which the equivalent input noise is to be calculated.
- NUMS

Indicates that only every \(N\) UM \(^{\text {th }}\) frequency point is stored for print-out. The contribution of every noise generator in the circuit is printed at every NUM \(^{\text {th }}\) frequency point. If NUMS is zero, no print-out is made. NUMS can be specified as a parameter or as an expression.

\section*{Example}
```

.ac dec 70 100k 10meg
.noise v(5) vin 70
...
*output control
.plot noise inoise onoise
.plot noise db(inoise) db(onoise)

```

Specifies vin as input noise reference and \(v(5)\) as the voltage at the summing point. The noise is averaged over seventy frequency points and the input and output results are to be plotted on the same graph, the limits of which are controlled by the .AC command.

\footnotetext{
(i)

An example of this type of analysis can be found in "Tutorials" on page 1341.
}

\section*{.NOISE_CORREL}

\section*{Noise Source Correlation}
.NOISE_CORREL VN1 VN2
+ \{f k_r k_i\}
Defines correlation coefficients between two independent noise sources.

\section*{Parameters}
- VN1, VN2

The two noise sources to be correlated.
- f, k_r, k_i
\(k \_r\) and k_i define the real and imaginary parts respectively of the correlation coefficient between the two noise sources vN1 and vN2 at frequency \(f\).

\section*{Example}
```

V1 1 0 four fund1 ma (1) 1 -90

+ noise table
+ 100 1e-5
+ 1k 1e-5
+ 10k 1e-5
R1 1 3 1k
V2 2 0 dc 2
+ noise table
+ 100 1e-5
+ 1k 1e-5
+ 10k 1e-5
.noise_correl V1 V2
*+ <f> <k_r> <k_i>
+ 100-1 0
+ 1k -1 0
+ 10k -1 0
R2 2 3 1k
R3 3 0 1k

```

\section*{.NOISETRAN}

\section*{Transient Noise Analysis}
```

.NOISETRAN FMIN=VAL FMAX=VAL NBRUN=VAL [NBF=VAL] [AMP=VAL]

+ [SEED=VAL] [NOMOD=VAL] [NONOM] [TSTART=VAL] [TSTOP=VAL]
+ [MRUN] [ALL] [NBBINS=VAL] [FMIN_FLICKER=VAL]

```

This command is used to control the transient noise analysis of a circuit and must be used in conjunction with a transient (. TRAN) analysis, and not with a Monte Carlo (.MC) analysis.

For further information, see the chapter on "Transient Noise Analysis" on page 1023.

It is possible to define the three parameters fmin, fmax and nbr for each noisy component; Resistor, Junction Diode, BJT—Bipolar Junction Transistor, JFET—Junction Field Effect Transistor, MESFET—Metal Semiconductor Field Effect Transistor, MOSFET, Independent Voltage Source and Independent Current Source. Please refer to the appropriate sections.

To reduce the CPU time, parallel noise runs are performed during a single transient analysis to compute the RMS noise results, instead of several runs. This allows larger circuits to be handled, larger number of runs and the ability to analyze a circuit with a CPU time close to a normal (noiseless) transient analysis.

Eldo will use the MRUN algorithm (perform several runs sequentially) by forcing the MRUN flag instead of the default single run algorithm if at least one of the conditions below is met:
- . PARt being used (for ADiT, OSR, and so on)
- . Chrsim present
- Presence of DELAY operators, T elements, FNS elements
- Use of local truncation error algorithm (@trunc option active)
- Mixed-mode simulation (presence of .A2D/.D2A commands)
- Use of IEM algorithm
- Use of Verilog-A

Two methods exist to generate transient noise signals. One uses a sum of sine waves with random phases. It is activated when FMIN is not zero. The second method, only activated when FMIN=0, uses gaussian random variables to generate noise sources. A noise source, with given frequency characteristics, will produce two different noise signals depending on the method used to generate them. These signals will have different instantaneous values but will have the same power and same frequency content.

\section*{Note}

The default values of eps, vintol, reltol, and hmax are changed in transient noise analysis from the values used in other analyses. For .noisetran, the defaults are eps \(=1.0 \times 10^{-6}\), vntol \(=1 \times 10^{-6}\) and reltol \(=1 \times 10^{-6}\). By default, Eldo is able to compute noise voltages down to about \(1 \mu \mathrm{~V}\). As most of the applications create higher levels of noise, this should be sufficient in most cases. In all other cases, it is advisable to increase the simulator accuracy.

For .noisetran, the default hmax value is hmax \(=1 /\left(2 x_{\text {Fmax }}\right)\). It is better to explicitly set a lower value for \(\operatorname{Hmax}\) than a high value for \(\operatorname{Fmax}\) to achieve the best accuracy possible.

When a .noisetran simulation is requested, transient analysis extracts (or extracts without any analysis type) will by default return only nominal values. Specify option DEFRMSNTR if both RMS values and nominal values should be dumped. In such a case, .EXTRACT TRAN extracts (or extracts without any analysis type) will return both RMS and nominal values: RMS values computed by .nOISETRAN, nominal values from the nominal transient analysis. This only has an effect for .nOISETRAN simulation with multiple run mrun specified. Use the analysis type NTR on the .EXTRACT command to select computation based on RMS.

If a single-run .nOISETRAN is performed, then the .EXTRACT command without any analysis will be interpreted only for the TRAN run, not for the NOISETRAN. In this case, the NTR keyword on the .Extract command must be specified. For example:
```

.NOISETRAN... MRUN
.EXTRACT <expression>

```
then expression will be evaluated for only the nominal run. If option defrmsntr is set, the nominal and the NTR analysis (on RMS waves) will be reported. Use the keyword NTR on the extract to obtain the RMS extract value.

If using .nOISETRAN in a single run analysis, then option Interp is disabled and a warning message displayed.

Use option Keep_hmpfile to generate a.\(h m p\) output file for transient noise analysis results. The .hmp file, of COU format (a legacy format), contains results for each NOISE analysis, and can be viewed with the waveform viewer. By default, it is not generated. If the nonom parameter is specified, then this option is always ignored and the .hmp file is not generated, This is because, with nомом specified, only one run, the noisy run, is performed. This is written directly to the regular.\(w d b\) file, without the need for an extra . \(h m p\) file, which is only used to compute RMS values when the simulation is complete. If not required for simulation results, the . \(h m p\) file should not be generated in order to save disk space.

\section*{Parameters}
- \(\quad\) FMIN=VAL

Lower limit of the noise frequency band.
- \(\quad\) FMAX=VAL

Upper limit of the noise frequency band.
FMIN and FMAX define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency band in the case of filters or oscillators and mixers that exhibit frequency conversion. FMIN is also used to specify the algorithm used to generate the noise sources in the time domain. When FMIN > 0 the noise sources are generated as a sum of NBF sinusoids. When fmin=0 another algorithm is used, generating noise sources with a continuous spectrum between 0 and FMAX.
- nbrun=Val

Defines the number of simulations which are performed with the noise sources included. This defines the accuracy of the noise analysis.

If \(\operatorname{NBRUN}=1\), the output voltages or currents stored in the binary output file are stored as simple voltages or currents. The noise voltages and currents of the nbrun simulations are stored together in the.\(w d b\) output file, which may be viewed with the waveform viewer. The file contains results for each NOISE analysis.

If nBRUN > 1, the binary output file will contain the RMS values of these curves. Otherwise, the binary output file will simply contain the noise voltage(s) or current(s).
When nомом is specified, nbrun is ignored and a warning generated.
- NBF=VAL

Specifies the number of sinusoidal sources with appropriate amplitude and frequency and with randomly distributed phase from which the noise source is composed. The default value is 50 . This parameter has no effect when Fmin is set to 0 .
- \(\quad \mathbf{A M P}=\mathrm{VAL}\)

This parameter is the noise source amplification factor and only affects internal noise computations. The noise is internally multiplied by this factor in order to differentiate electrical noise from numerical noise and afterwards, when RMS noise values are calculated, the values are divided by this factor again to provide correct results. This factor should only be used if the noise level is very low (for example below \(1 \mu \mathrm{~V}\) ). Care must be taken if this feature is used as some circuits are non-linear, even with small signals, which may cause incorrect results. The default value of amp is 1 .
- SEED=VAL

Used to initialize the random number generator. Must be an integer between 0 and \(2^{31}-1\). Performing two noise simulations will provide the same RMS noise results. The default value is 0 .
- \(\quad\) NOMOD=0|1|2

Switch to select the noise source for MOSFET devices:
0 Noise simulation with thermal and flicker noise. Default.
1 Noise simulation without thermal noise.
2 Noise simulation without flicker noise.
- NONOM

No nominal simulation. Specifies that only one noisy simulation should be performed and the nominal simulation is suppressed. If specified, the. hmp file is never generated, even if option keep_hmpfile is also specified. When nonom is specified, nbrun is ignored and a warning generated.
- TSTART=VAL

Specifies the first time point from which the circuit generates noise (before tStart the circuit is noiseless). Default value is 0 .
- TSTOP=VAL

Specifies the last time point of the transient noise analysis. After TSTOP the circuit no longer generates noise. Default value is TSTOP of the .TRAN command.
- MRUN

Multiple run. Forces the algorithm to perform several runs sequentially to compute the RMS noise results. Specify this if you do not want the algorithm to perform parallel noise runs. Histograms will be written to the output file if the number of simulation runs is greater than the number specified by nbbins.
- all

Forces Eldo to dump the results of the simulation in the ASCII output files (by default these waves are not dumped, since they are normally unusable).
- \(\quad\) NBBINS \(=\) VAL

Specifies the number of bins for the histogram produced when the transient noise is used with the .extract command. Default is 10.
- FMIN_FLICKER=VAL

Specifies the lower limit of the noise frequency band for the flicker noise source when FMIN=0. If FMIN>0 this parameter will be ignored. Optional.

\section*{Example}
```

.NOISETRAN ...
.extract TRAN label = L1 ...
.extract label = L2 ...
.extract NTR label = L3 ...

```

Here only one value computed for both L1 and L2, based on the nominal run, and one value for L3 (computed from RMS values). With option Defrmsntr, two extract values will be returned for both L1 and L2, and one for L3.

\section*{Related options}

See "DEFRMSNTR" on page 999, "NODEFRMSNTR" on page 1004 and "KEEP_HMPFILE" on page 1002.

\section*{.NOTRC}

\section*{Suppress Netlist from an Output File} .NOTRC

This command suppresses the rewriting of the circuit description file in the ASCII output (.chi) file. You can specify this command anywhere in the netlist, it does not need to be placed immediately after the first line.

\section*{Example}
```

example title
.notrc
r1 1 2 5
..
.end

```

Related options
See "NOTRC" on page 1005 and "NOTRCLIB" on page 1005.

\section*{.NWBLOCK}

\section*{Partition Netlist into Newton Blocks}
.NWBLOCK [RELTOL=value] [VNTOL=value] list_of_nodes
This command allows the user to control the way Eldo will partition the netlist into several Newton Blocks. Additionally, blocks can have different accuracies.

There can be several . NWBLOCK commands. Each . NWBLOCK will result in the creation of a Newton Block.

\section*{Parameters}
- list_of_nodes

The list of nodes to be assigned to a Newton Block. The wildcard character ' \(\star\) ' is allowed as shown in the following example:
```

.NWBLOCK X1.*

```
- RELTOL=value

Controls the accuracy of the Newton Block. Optional. Same meaning as the reltol global parameter that can be specified with:

\section*{.OPTION RELTOL=val}

The scope of visibility is limited here to the node/instances referred to in the . NWbLock command.
- vNTOL=value

Controls the voltage accuracy of the simulator. Optional. Same meaning as the vntol global parameter that can be specified with:
.OPTION VNTOL=val
The scope of visibility is limited here to the node/instances referred to in the . nWblock command.

\section*{Notes}
- If a node is referred to in several . NWblock commands, the node will belong to the first block created via the .nwblock command.
- . nWblock commands are used in transient analysis (TRAN) only. . nwblock is ignored for DC analysis.
- For nodes which do not appear in any . NWblock commands: if the node cannot be solved by OSR, they will be grouped into another newton block.
- Once nodes have been assigned to a Newton Block, Eldo may decide to group together some or all of the newton blocks just created, for the sake of simulation efficiency.

\section*{.OBJECTIVE}

\section*{Optimization Objectives}
```

.OBJECTIVE

+ EXTRACT_INFO [LABEL=NAME]
+ {\$MACRO|FUNCTION}
+ OBJECTIVE_INFO
+ [SCALING_INFO]
+ [PRINT_INFO]

```

The .objective command is based on the extract construct, and specifically dedicated to optimization. Some restrictions are imposed and the semantic is different in some situations. The specification of design objectives has been simplified.

For the complete description of optimization capabilities, see the separate chapter Optimizer in Eldo.

\section*{.OP}

\section*{DC Operating Point Calculation}
```

.OP [[KEYWORD] T1 {[KEYWORD] TN}]
.OP TIME=VAL|END [STEP=VAL] [TEMP=VAL]
.OP DC=VAL [DC2=VAL] [STEP=VAL] [TEMP=VAL]

```

This command forces Eldo to determine the DC operating point of the circuit with inductors short-circuited and capacitors opened. If either the specified simulation time is reached or one of the conditions described in the "optional parameters" below is fulfilled, the operating point is saved to the .chi file.

If no parameter is specified, the operating point information is saved for DC prior to AC or first DC analysis in the case of a DC sweep.

Additional information concerning the operating points such as power dissipation, node voltages and source currents are written to the .chi output file.

The result table generated by the .OP command includes all OP results in addition to node voltages and device currents. These terms (BETADC, BETAAC, CXS, VTh_D) are printed out in the OP table, and can also be plotted/printed.

When performing operating point calculation at time \(t\), with .OP \(t\), Eldo saves voltages on nodes and static currents in branches, and outputs them as an Operating Point. However, since only static current is taken into account, the current results might be different from the transient current results at the same time, which also include dynamic currents (for example \(i=C \times d v / d t\) ).

\section*{Parameters}
- KEYWORD

Can be one of the strings: all, def, brief, current, volt.
Select all or def (synonyms) to display OP information for both current and voltage nodes (default).
Select brief or current (synonyms) to display OP information only for currents of each element, a limited set of information compared to the ALL/DEF case.

Select volt to display OP information only for the voltage nodes.
- T1, TN

Simulation times at which operating point information will be recorded. The parameter END can be specified as a simulation time.
- TIME=VAL

Simulation time for which .op results are written.
- END

Forces Eldo to output the . OP information after a transient analysis (.TRAN) if specified.
- Step=VAL

Step value for which .op results are written. This is the case for when the .STEP command is used.
- TEMP=VAL

Current temperature for which . op results are written.
- DC=VAL

DC sweep value for which . op results are written.
- DC2=VAL

Second DC value for which . Op results are written in cases where a double DCSWEEP analysis is performed.

Note
A .OP command is always automatically performed prior to an AC analysis. If no other analysis is specified, a .OP command forces a DC analysis to be performed after the operating point has been calculated.

For MOSFET and BJT, Eldo prints in the DCOP point table the operating region of the device. The following messages are written:
- For MOSFET:
```

if ((vgs - vgt) < 0) "SUBTHRESHOLD"
else if ((vds - vdss) < 0) "LINEAR"
else "SATURATION"

```
- For BJT:
```

if (VBC > VBCSAT)
if (VBE > 0) "SATURATION"
else "INVERSE"
else
if (VBE > 0) "ON"
else "OFF"

```

VBCSAT can be specified in the . OPtion command. Default is 0 .

\section*{Options}
- .OPTION OPTYP=VAL

Used to change the way Operating Point information related to MOSFETs is displayed in the ASCII output file.
- .OPTION OPTYP=1

Full operating point table is displayed. This is the default.
- .OPTION OPTYP=2

Can be specified only when either the -st flag or the STvER option are set. Used to print the reduced operating point information for the MOSFET models (see the Spice documentation for more details). Otherwise equivalent to optyp \(=1\). This can be used with UDM and BSIM4 models.
- .OPTION OPTYP=3

Output compatible with Spice3e2.
Table 10-17 lists the character string displayed in the Operating Point table for the different optyp values. Elements on the same line are synonymous: that is, the same value would be printed if optyp changes.

Table 10-17. Operating Point-optyp values
\begin{tabular}{|c|c|c|c|}
\hline Default & optyp=3 & When -st flag or STVER option is set & When -st flag or STVER option is set \& optyp=2 \\
\hline ID & ID & ID & ID \\
\hline & & IS & \\
\hline & & IB & \\
\hline VGS & VGS & VGS & VGS \\
\hline VDS & VDS & VDS & VDS \\
\hline VBS & VBS & VBS & VBS \\
\hline VTH & VTH & VTH & VTH \\
\hline VDSAT & VDSAT & VDSAT & VDSAT \\
\hline & & & gm \\
\hline & & & gm \\
\hline GM & GM & & \\
\hline GDS & GDS & & \\
\hline GMB & GMB & & gmbs \\
\hline & & Ibd & Ibd \\
\hline & & Ibs & Ibs \\
\hline & & Gdd & Gbd \\
\hline & & Gdg & Gbs \\
\hline & & Gds & \\
\hline & & Gsd & \\
\hline & & Gsg & \\
\hline
\end{tabular}

Table 10-17. Operating Point-optyp values
\begin{tabular}{|l|l|l|l|}
\hline Default & optyp=3 & \begin{tabular}{l} 
When -st flag or \\
STVER option is set
\end{tabular} & \begin{tabular}{l} 
When -st flag or STVER \\
option is set \& optyp=2
\end{tabular} \\
\hline & & Gss & \\
\hline
\end{tabular}

An explanation of some of these parameters is provided below:
\(I b d \quad\) Bulk-drain current through the parasitic \(B D\) diode
Ibs Bulk-source current through the parasitic \(B S\) diode
VTH Internal threshold OP dependent; see the Eldo Device Equations Manual for how it is computed

VSS or VDSATSaturation voltage at DCOP
Gxy Derivative of static current on node \(x\) with respect to \(V y ; x\) and \(y\) can be one of \(D, G, S, B\)

Cxy Derivative of charge on node \(x\) with respect to \(V y ; x\) and \(y\) can be one of \(D, G\), S, B

Isub Subthreshold current component
As shown in Table 10-17, with the -st flag or stver option set and optyp not set or not 2, then Eldo reports several Gxy terms, where Gxy stands for derivative of current on pin \(x\) with respect to voltage on pin \(y\). For example, \(G d s\) is the derivative of the current on the Drain with respect to the voltage on the Source. In all other cases, just three conductances values are reported:
- \(\quad G M\) is the derivative of \(I D S\) with respect to \(V G S\)
- GDS is the derivative of IDS with respect to VDS
- GMBS is the derivative of \(I D S\) with respect to VBS

In the OP table for BSIM3v3, Eldo also displays VBI and PHI:
PHI Surface potential at strong inversion
VBI Built-in voltage for the PN junction between the substrate and the source

Table 10-18. Operating Point-optyp values Dynamic Part for Charge Control Model
\begin{tabular}{|l|l|l|l|}
\hline Default & optyp=3 & \begin{tabular}{l} 
When -st flag or \\
STVER option is set
\end{tabular} & \begin{tabular}{l} 
When -st flag or STVER \\
option is set \& optyp=2
\end{tabular} \\
\hline Cdd & Cddb & Cdd & \\
\hline Cdg & Cdgb & Cdg & \\
\hline Cds & Cdsb & Cds & \\
\hline Cdb & & Cdb & \(\mathrm{Cdb}+\mathrm{CJDB}\) \\
\hline Cgd & Cgdb & Cgd & \(\mathrm{Cgd}+\mathrm{CVGD}\) \\
\hline Cgg & Cggb & Cgg & \\
\hline Cgs & Cgsb & Cgs & \(\mathrm{Cgs}+\mathrm{CVGS}\) \\
\hline Cgb & & Cgb & \\
\hline Csd & & Csd & \\
\hline Csg & & Csg & CVGB \\
\hline Css & & Csb & \\
\hline Csb & & Cbd & CJSB \\
\hline Cbd & Cdbd & Cbg & \\
\hline Cbg & Cbgb & Cbb & \\
\hline Cbs & & & \\
\hline Cbb & & & \\
\hline
\end{tabular}

Table 10-19. Spice3e Capacitance / Eldo Capacitance
\begin{tabular}{|l|l|}
\hline Spice3e capacitance & Relationship with Eldo capacitance \\
\hline Cbsb & \(-(\mathrm{Cbg}+\mathrm{Cbd}+\mathrm{Cbb})\) \\
\hline Cbdb & Cbd \\
\hline Cbgb & Cbg \\
\hline Cdsb & \((\mathrm{Cgg}+\mathrm{Cgd}+\mathrm{Cgb}+\mathrm{Cbg}+\mathrm{Cbd}+\mathrm{Cbb}+\mathrm{Csg}+\mathrm{Csd}+\mathrm{Csb})\) \\
\hline Cddb & \(-(\mathrm{Cgd}+\mathrm{Cbd}+\mathrm{Csd})\) \\
\hline Cdgb & \(-(\mathrm{Cgg}+\mathrm{Cbg}+\mathrm{Csg})\) \\
\hline Cgsb & \(-(\mathrm{Cgg}+\mathrm{Cgd}+\mathrm{Cgb})\) \\
\hline
\end{tabular}

Table 10-19. Spice3e Capacitance / Eldo Capacitance
\begin{tabular}{|l|l|}
\hline Spice3e capacitance & Relationship with Eldo capacitance \\
\hline Cgdb & Cgd \\
\hline Cggb & Cgg \\
\hline
\end{tabular}

In SPICE operating point display the \(\boldsymbol{C b s}\) and \(\boldsymbol{C b} \boldsymbol{d}\) values are bulk-source and bulk-drain currents correspondingly. These results do not correspond to Eldo \(\boldsymbol{C b s}\) and \(\boldsymbol{C b d}\) since these last two items correspond to capacitances.

\section*{Example}
```

R1 N1 N2 R1
.PARAM R1=1k
.STEP PARAM R1 1k 10k 1k
.TRAN 1n 100n
.OP
.OP TIME=9n STEP=5k
.END

```

In the above example, an Operating Point will be determined for a resistance of \(5 \mathrm{k} \Omega\) at time 9 ns .

\section*{Note}
\(\qquad\)
The .op command may be used to run AC and NOISE analyses from within a .tran command at specified times, see "AC in the middle of a .TRAN" on page 543 for more details.

\section*{.OP_DISPLAY}

\section*{DC Operating Point Display}
```

.OP_DISPLAY

+ [MODEL=model_name]
+ [VTMOD=0|1|2]
+ [VTVDS=vds]
+ [VTCIDS=ids_norm]
+ [VTVGSMIN=vgsmin]
+ [VTVGSMAX=vgsmax]

```

This command enables the printing of alternative threshold voltage (VT) values for MOS devices. It is only active when a .OP command is specified. The VT results are written to the OP section of the ASCII .chi output file. The alternative calculation methods are: maximum transconductance algorithm threshold (MAXGMVT) and constant current threshold (VTC).

These alternative methods ensure the electrical test limits of MOSFETs in manufacturing are aligned with the SPICE models. By default, the standard algorithm is based only on model parameters and is not directly measurable on a physical transistor.

If no parameters are specified, or if vтмоd is set to 0 (see below), the standard method of calculating VT is used, so the command is ignored. Multiple commands can be specified to display different reports, that is, it is possible to print both MAXGMVT and VTC in the .chi file.

\section*{Parameters}
- MODEL=model_name

Specifies the models to which this command applies. model_name can contain the wildcard character '*'. If this keyword is not specified, the command will be applied to all models, equivalent to specifying MODEL=*.
- VTMOD=0|1|2

Specifies the alternative method to calculate VT.
VTMOD=0
Eldo standard algorithm. This is the default value.
VTMOD=1
Eldo will calculate and report MAXGMVT.
```

VTMOD=2

```

Eldo will calculate and report VTC.

\section*{- VTVDS}

Specifies the default VDS (drain source voltage) value for Eldo to use in the VT calculations. See the MAXGMVT, VDSATC and VTC extract functions for further details. Default value is 0.1.
- vtcids

Specifies the default IDS_NORM (normalized drain source current) value for Eldo to use in the VT calculations. See the VDSATC and VTC extract functions for further details.
Default value is 600 nA .
- vtvgsmin

Specifies the default VGSMIN (minimum gate source voltage) value for Eldo to use in the VT calculations. See the MAXGMVT, VDSATC and VTC extract functions for further details. Default value is LV9(Mxx) - 0.5 .
- VTVGSMAX

Specifies the default VGSMAX (maximum gate source voltage) value for Eldo to use in the VT calculations. See the MAXGMVT, VDSATC and VTC extract functions for further details. Default value is LV9(Mxx) +0.5 .

\section*{Example}
```

.op
.op_display model=*

+ VTMOD=1
+ VTVDS=0.1
+ VTCIDS=600e-9
.op_display model=*
+ VTMOD=2

```

Example extract of .chi file:
\begin{tabular}{|c|c|c|c|c|}
\hline & X1. M1 & X2.M1 & X3.M1 & X4.M1 \\
\hline MODEL & NSHORT. 3 & NSHORT. 3 & NSHORT. 3 & NSHORT. 3 \\
\hline ID & 0.0 & 0.0 & 0.0 & \(4.56889437 \mathrm{E}-08\) \\
\hline Ibd & 0.0 & 0.0 & 0.0 & -1.00000000E-14 \\
\hline Ibs & 0.0 & 0.0 & 0.0 & 0.0 \\
\hline VGS & \(3.00000000 \mathrm{E}+00\) & 0.0 & 0.0 & 0.0 \\
\hline VDS & 0.0 & 0.0 & 0.0 & \(3.00000000 \mathrm{E}+00\) \\
\hline VBS & 0.0 & 0.0 & 0.0 & 0.0 \\
\hline VTH & \(3.67156515 \mathrm{E}-01\) & \(3.67156515 \mathrm{E}-01\) & \(3.67156515 \mathrm{E}-01\) & \(3.63441805 \mathrm{E}-01\) \\
\hline VDSAT & \(1.54552476 \mathrm{E}+00\) & \(4.53584187 \mathrm{E}-02\) & \(4.53584187 \mathrm{E}-02\) & \(4.53582818 \mathrm{E}-02\) \\
\hline [...] & & & & \\
\hline Region & linear & subthreshold & subthreshold & subthreshold \\
\hline VTH_D & \(2.63284349 \mathrm{E}+00\) & -3.67156515E-01 & -3.67156515E-01 & -3.63441805E-01 \\
\hline VTC & \(3.67032691 \mathrm{E}-01\) & \(3.67032691 \mathrm{E}-01\) & \(3.67032691 \mathrm{E}-01\) & \(3.67032691 \mathrm{E}-01\) \\
\hline MAXGMVT & \(3.28272746 \mathrm{E}-01\) & \(3.28272746 \mathrm{E}-01\) & \(3.28272746 \mathrm{E}-01\) & \(3.28272746 \mathrm{E}-01\) \\
\hline & X1.M2 & X2.M2 & X3.M2 & X4.M2 \\
\hline MODEL & PSHORT. 1 & PSHORT. 1 & PSHORT. 1 & PSHORT. 1 \\
\hline ID & 0.0 & 0.0 & 0.0 & \(5.94230571 \mathrm{E}-03\) \\
\hline Ibd & 0.0 & 0.0 & 0.0 & -6.87153080E+00 \\
\hline Ibs & 0.0 & 0.0 & 0.0 & 0.0 \\
\hline VGS & \(3.00000000 \mathrm{E}+00\) & 0.0 & 0.0 & 0.0 \\
\hline VDS & 0.0 & 0.0 & 0.0 & \(3.00000000 \mathrm{E}+00\) \\
\hline
\end{tabular}
```

VBS 0.0 0.0 0.0 0.0
VTH -3.57021910E-01 -3.57021910E-01 -3.57021910E-01 -3.20172698E-01
VDSAT -4.39505891E-02 -4.39532068E-02 -4.39532068E-02 -2.04057023E+00
[...]
Region subthreshold subthreshold subthreshold subthreshold
VTH_D -3.35702191E+00 -3.57021910E-01 -3.57021910E-01 -3.20172698E-01
VTC -3.53187113E-01 -3.53187113E-01 -3.53187113E-01 -3.53187113E-01
MAXGMVT -3.29728569E-01 -3.29728569E-01 -3.29728569E-01 -3.29728569E-01

```

\section*{.OPTFOUR}

\section*{FFT Post-processor Options}
```

.OPTFOUR [TSTART=VAL|EXPR] [TSTOP=VAL|EXPR] [NBPT=VAL] [FS=VAL]

+ [NORMALIZED=0|1] [NORMALIZATION_FACTOR=val] [INTERPOLATE=0|1|2|3]
+ [NOROUNDING[=1]] [RAPWIN=VAL]
+ [WINDOW=name] [ALPHA=VAL] [BETA=VAL] [PADDING=1|2|3]
+ [FMIN=VAL] [FMAX=VAL] [FNORMAL=freq] [DISPLAY_INPUT=0|1]

```

Used to supply the options for the FFT post-processor. See also ".FOUR" on page 673.

\section*{Setting Parameters}

The following four parameters are used to specify the time window on which the FFT will be performed. This can be summarized by Table 10-20, which provides the values of TSTART, TSTOP, FS, NBPT for all possible cases.
- TSTART

Time value from which the time window will start. Default value is option STARTSMP if specified, or TSTART from .TRAN, or TSTOP-NBPT/FS if all three other parameters specified.
- tSTOP

Time value that specifies the end of the time window. Default value is TSTART from .TRAN, or TSTART+NBPT/FS if all three other parameters specified.
- FS

Sampling frequency. Default value is NBPT/(TSTOP-TSTART).
- NBPT

Number of points to be used in the time window. Default value is 1024 , or (TSTOP-TSTART) \(\times\) FS if FS specified.

Table 10-20. Default Values for Time Window Parameters
\begin{tabular}{|l|l|l|l|}
\hline TSTART & TSTOP & FS & NBPT \\
\hline User Defined & TSTOP & NBPT/(TSTOP-TSTART) & 1024 \\
\hline STARTSMP or TSTART & User Defined & NBPT/(TSTOP-TSTART) & 1024 \\
\hline STARTSMP or TSTART & TSTOP & User Defined & (TSTOP-TSTART)*FS \\
\hline STARTSMP or TSTART & TSTOP & NBPT/(TSTOP-TSTART) & User Defined \\
\hline User Defined & User Defined & NBPT/(TSTOP-TSTART) & 1024 \\
\hline User Defined & TSTOP & User Defined & (TSTOP-TSTART)*FS \\
\hline User Defined & TSTOP & NBPT/ (TSTOP-TSTART) & User Defined \\
\hline
\end{tabular}

Table 10-20. Default Values for Time Window Parameters
\begin{tabular}{|l|l|l|l|}
\hline TSTART & TSTOP & FS & NBPT \\
\hline STARTSMP or TSTART & User Defined & User Defined & (TSTOP-TSTART)*FS \\
\hline STARTSMP or TSTART & User Defined & NBPT/(TSTOP-TSTART) & User Defined \\
\hline StARTSMP or TSTART & \begin{tabular}{l} 
TSTART+NBPT \\
/FS
\end{tabular} & User Defined & User Defined \\
\hline User Defined & User Defined & User Defined & (TSTOP-TSTART)*FS \\
\hline User Defined & User Defined & nBPT/(TSTOP-TSTART) & User Defined \\
\hline User Defined & \begin{tabular}{l} 
TSTART+NBPT \\
/FS
\end{tabular} & User Defined & User Defined \\
\hline TSTOP-NBPT/FS & User Defined & User Defined & User Defined \\
\hline User Defined & User Defined & User Defined & User Defined \\
\hline
\end{tabular}

\section*{Note}


If both fs and NBPT parameters are specified by the user then NBPT will be calculated using the relation NBPT \(=(\) TSTOP - TSTART \() *\) FS.

- NORMALIZED

Specifying 1 means that all the points of the result are multiplied by \(2 /\) nBPr . Default.
Specifying 0 means no normalization of the results.
- NORMALIZATION_FACTOR

Replaces the default factor (2/nBPt) which is applied to FFT results when normalized is set to 1 . It is ignored if normalized is set to 0 .
- interpolate

Sets type of interpolation:
\(0=\) No interpolation (default)
\(1=\) Linear interpolation
2 = Cubic Spline interpolation
3 = Blocker Sampler interpolation
- NOROUNDING [=1]

By default, Eldo truncates and rounds tstart and tstop values at 1 ps . If keyword nOROUNDING is specified, this rounding is not performed.

\section*{- RAPWIN}

Represents a fraction of the FFT window. See description at end of Notes section below.

\section*{Notes}
1. FFT is much faster when the NBPT parameter (either user given, or computed from the three other parameters) can be a product of powers of 2,3 and/or 5 so that fast algorithms can apply. For example, 1022 can be divided by 2, but is not a good candidate; \(1024=2^{10}\) or \(960=3 \times 5 \times 2^{6}\) are better candidates. In such cases, the FFT program will make use of several optimizations which do not alter the FFT results.
2. The last time point value actually taken into account by FFT is the value at time: тstop\(1.0 / \mathrm{Fs}\). This is to deal with the fact that when FFT is done on a circuit which is in steadystate mode, time value F (тStop) equals the time value F (тStart), and hence that last value must not be used for the FFT since FFT must be computed on a full number of periods.
3. tStart and tstop time values can be specified as results of an expression that follows the .EXtract syntax, see ".EXTRACT" on page 637 . When the expression can be measured, FFT sampling will start.

\section*{Caution}

When the parameter \(\mathbf{T S T O P}\) is specified as an expression and the parameter nBPt is used, then it is impossible for Eldo to determine the sampling frequency before the simulation. Furthermore, Eldo cannot compute exactly the points which will be used to compute the FFT. Therefore, the parameter interpolate cannot be set to 0 (no interpolation). In this case a warning message will be displayed by Eldo and the parameter interpolate will be set to 2 .
4. A very important point is related to the interpolate parameter: FFT must be done on equally-spaced time value points. However, the time points computed by an analog simulator such as Eldo are not equally spaced. There are two possibilities to obtain the equally-spaced points required by FFT:
- Force Eldo to compute values at least on the points requested by the FFT (and in between Eldo can do smaller time steps if needed),
- Interpolate between the time values points computed 'freely' by Eldo: this interpolation can be a LINEAR interpolation (INTERPOLATE \(=1\) ) or a higher order interpolation (INTERPOLATE \(=2\) : a cubic SPLINE is used).

FFT results are better when no interpolation occurs. For this reason the parameter interpolate defaults to 0 . In such a case, Eldo will compute time-value points at least every 1/Fs seconds.

If interpolate is set to 1 or 2, Eldo will compute its time steps according to the activity in the design and the equally-spaced time points required by the FFT will be interpolated from that
time-domain waveform generated by Eldo. interpolate=2 gives better results than INTERPOLATE=1.

The .optrour interpolate command and . option fregsmp are independent (prior to the 2008.1 release they were not). With this scheme, and with FREQSMP not set, then FFT results might be not as accurate as before, because the time step is only computed very accurately inside the FFT window. The FFT results might be not accurate if the signal has not been computed with enough accuracy when arriving at the beginning of the window. Use parameter RAPWIN to handle this, which represents a fraction of the FFT window: if positive, Eldo will start applying the time constraint which will prevail in the FFT window [tstart, tstor] in the window [TSTART - RAPWIn \(\times\) (TSTOP - TSTART), TSTART]. Alternatively, it is possible to use FREQSMP, or HMAX, to impose some constraints to the time step outside the FFT window.

\section*{PADDING Parameter}

Specifies where to add zeros inside the FFT input window: only used if tStart, tstop, nbpt and \(\mathbf{F S}\) are given and NBPT \(>(\mathbf{T S T O P}-\mathbf{T S T A R T}) \times\) FS.

PADDING can be set to:
\(1 \quad\) Zeros are added at the beginning of the FFT input window
2 Zeros are added at the end of the FFT input window
3 Zeros are added evenly at the beginning and at the end of the FFT input window.

\section*{Display Parameters}
- FMIN

Starting frequency used inside the FFT result window.
- FMAX

Last frequency used inside the FFT result window.

> Note
> FMIN and FMAX parameters are not used for an FFT on an FMODSST signal.
- FNORMAL=freq

Adjusts the results around the Y -axis so that the point for the specified frequency is 0.0 .
- DISPLAY_INPUT

Generates an additional transient waveform of the exact data points used for the FFT calculation. This FFT_INPUT waveform contains equally-spaced time value points from START time to one datapoint short of the STOP time.
\(0=\) do not create the extra FFT_INPUT transient waveform (default)
\(1=\) create the FFT_INPUT waveform if a .PLOT or .PROBE command exists for the .four item. For example:
```

.four label=test v(foo)
.plot four test

```
with display_Input=1 the FFT_INPUT(TEST) waveform will be generated inside the TRAN folder in the EZwave Waveform List panel.
See Performing a Fast Fourier Transform in the EZwave User's and Reference Manual.

\section*{Sampling WINDOW Parameter}

Specifies the Sampling Window to be used. The following parameters are allowed:
RECTANGULAR (default)
PARZEN
BARTLETT
WELCH
BLACKMAN
BLACKMAN7
KLEIN
HAMMING
HANNING
KAISER
DOLPH_CHEBYCHEV

\section*{Associated Parameters}
- ALPHA

Used when the window in Dolph_chebychev or hanning.
- BETA

Used when the window is kaiser. Constant which specifies a frequency trade-off between the peak height of the side lobe ripples and the width of energy in the main lobe.

Please refer to the EZwave User's Manual for further details of the windowing equations.

\section*{Example}
.optfour tstart=xdown \((V(1), 2 u, 1)\) tstop=xdown (V(1), 2u,1000) ..
.four ...
Eldo computes an FFT with 1000 periods of signal \(V(1)\). This shows how tstart and tstop time values can be specified as results of an expression. When the expression can be measured, FFT sampling will start.
```

.optfour tstart=0 tstop={xdown(V(1),10m,13)} nbpt=10000

```

When the parameter tstop is specified as an expression and the parameter nbpt is used, then it is impossible for Eldo to determine the sampling frequency before the simulation. Eldo cannot
compute exactly the points which will be used to compute the FFT. Therefore, the parameter interpolate cannot be set to 0 (no interpolation). In this case the following warning message will be displayed by Eldo and the parameter interpolate will be set to 2 .
```

Warning: .OPTFOUR : parameter INTERPOLATE is set to 2 because NBPT is
given and TSTOP is an expression

```

\section*{.OPTIMIZE}

\section*{Optimization}
```

.OPTIMIZE [qualifier=value {, qualifier=value }]

+ [PARAM=list_of_parameters | *]
+ [RESULTS=list_of_targets | *]

```

The global specification of an optimization configuration acting on all the analyses specified in the circuit netlist is done using the .optimize command.

For the complete description of optimization capabilities, see the separate chapter Optimizer in Eldo.

\section*{.OPTION}

\section*{Simulator Configuration}
. OPT[ION] OPTION[=VAL] \{OPTION[=VAL]\}
The . OPtion command allows the user to modify Eldo execution behavior by allowing the setting of parameter values other than the default ones.
(1)

For the complete description of options available, see the separate chapter "Simulator and Control Options" on page 939.

\section*{.OPTNOISE}

\section*{AC Noise Analysis}
```

.OPTNOISE [ALL ON|OFF] [<CLASS> ON|OFF]

+ [R ON|OFF|<max>] [OUTSOURCE ON|OFF] [NSWEIGHT <FILENAME>]
+ [SORT D|V TD|TV [SN <n>|SV <value>]] [NBW <FMIN> <FMAX>]

```
. OPTNOISE allows more flexibility in the output of the AC noise analysis results: noisy elements can be sorted in different ways, and a weight function can be applied before printing out the noise contribution. The . OPTNOISE command must be used in conjunction with the . AC and .nOISE analyses. .OPTNOISE has no effect on .SSTNOISE analysis and results.

\section*{Parameters}
- all

Specifies that all devices should contribute to the total noise.
- CLASS

Is one of the following keywords: mos, but, npn, pnp, nmos, pmos, diode, Jfet, njf, pJf. For example: mos off means all MOS devices source noise is turned OFF.
- outsource

Specifies that printing out of NOISE information in the ASCII output file must be turned ON or OFF.
- NSWEIGHT <filename>

Reads a file for weighted functions: the format of this file is shown in "Format of files containing weight" on page 773.
- R
on: all resistors are assumed to be noisy.
OFF: all resistors are assumed to be noiseless
MAX: all resistors above MAX are assumed to be noisy.
- SORT

Choose the way the information is displayed in the ASCII output file:
D: sort by device,
v: sort by value,
TD: sort by technology (CLASS), and in each CLASS by device,
Tv: sort by technology (CLASS), and in each CLASS by value,
SN <n>: list the highest \(n\) contributions: default \(n=20\)
sv <value>: list the device contribution until value in \% of the total noise is exceeded. Default value \(=0.95\) ( \(95 \%\) ).

\section*{- NBW}
stands for Noise BandWidth, which can be different than that of AC band: RMS Average is computed on this bandwidth which defaults to the AC bandwidth. FMIN and FMAX values define the frequency band of this noise bandwidth.

\section*{Multiple output noise}

Several .noise commands can be given for the same run. Eldo will then perform as many NOISE analyses as required. See the OUTPUT/post-processing section below for reporting information.

\section*{Output/Post-processing}
- A noise table that contains general information is first printed out: for each output node there appears the noise RMS value, the Average and total noise power, the maximum and minimum noise power contribution, and the frequency at which these last two values are obtained. In case the weighting function is applied, both weighted and unweighted values are dumped, but for other information below, just weighted or unweighted values will come depending on the content of the .OPTNOISE command.
- For each output noise, total noise source values are displayed, sorted according to the .OPTNOISE specification (SORT SN or SORT SV arguments).
- For each output and each listed element which appears in 2), the table total noise \(=f(F R E Q)\) is printed out, each <n> frequency points, where \(n\) is the number specified in the . noise command. Here, frequencies are those of AC: an asterisk (*) should appear to mark the frequency corresponding to Noise Bandwidth. If there is no sorting of information, then the regular SPICE output will be printed out, with detail of the contribution of each device.
- Regular frequency output table: this is the content of .PRINT NOISE.
- A file <namecir>_nsa.cou will also be created, containing the noise response of the devices selected by the SORT command option.
- By default, the noise response of devices selected by the sOrt command option are merged into the NOISE folder of the.\(w d b\) file. Use option nSafile_format to control the output generated. Set to cou for backward compatiblity (pre-2009.2) behavior to create a separate <netlist>_nsa.cou file. Set to none to disable the creation of this file if you are only interested in the table inside the .chi file. Default is wdb.

\section*{Format of files containing weight}

\section*{References:}
1. IEEE Standard Methods and Equipment for Measuring the Transmission Characteristics of Analog Voice Frequency Circuits. (IEEE Std. 743-1984)
2. SCAMPER Reference Manual, Rel.501, 1990 (noise analysis and option)
3. SCAMPER User's Guide, Rel.501,1990

C-Message filter is a frequency-weighting characteristic, used for measurement of noise in voice frequency communications circuits and designed to weight noise frequencies in proportion to their perceived annoyance effect to a typical listener in telephone service. Reference point 1000 Hz .

Format of the noise weight table:
```

FreqS|* FreqE|* <flatweight> <weightunit>

+ <freq_interpolation_type>
f1 w1
fn wn

```
- FreqS

Starting frequency for noise weight. If "*" is given then the first frequency in the freq/weight data table will be taken as the starting frequency. Units in Hertz.
- FreqE

Ending frequency for noise weight. If " \(*\) " is given then the last frequency in the freq/weight data table will be taken as the ending frequency. Units in Hertz.
- flatweight

If the flatweight value is given, then it will be taken as a constant (flat) noise weight over the given frequency band (no noise outside the band). The freq/weight data table, if any, will be ignored. If " \(\star\) " is given in place of FreqS and/or FreqE, then the corresponding value will be taken from the \$frequency line in the scamper netlist.
- weightunit

Units of the flatweight or the weight values in the freq/weight data table:
DBL weight given in decibels loss (default)
DB weight given in decibels
MAG weight given in numerical value (for noise power)
- freq_interpolation_type

Type of interpolation for noise weight between frequencies.
LOG logarithmic frequency interpolation (default)
LIN linear frequency interpolation
- fi wi

Table of frequency and associated weighting values. More than one pair could be given on one line.

\section*{Example weight file}
```

\
' this is a comment
100 4000 DBL LOG ' weight is in DBL, LOG interpolation

```
\begin{tabular}{|c|c|c|c|c|}
\hline 60 & 55.7 & ' & 2 & \\
\hline 100 & 42.5 & ' & 2 & \\
\hline 200 & 25.1 & ' & 2 & \\
\hline 300 & 16.3 & ' & 2 & \\
\hline 400 & 11.2 & ' & 1 & \\
\hline 500 & 7.7 & ' & 1 & \\
\hline 600 & 5.0 & ' & 1 & \\
\hline 700 & 2.8 & ' & 1 & \\
\hline 800 & 1.3 & ' & 1 & \\
\hline 900 & 0.3 & ' & 1 & \\
\hline 1000 & 0.0 & ' & 0 & ' reference point \\
\hline 1200 & 0.4 & ' & 1 & \\
\hline 1300 & 0.7 & ' & 1 & \\
\hline 1500 & 1.2 & ' & 1 & \\
\hline 1800 & 1.3 & ' & 1 & \\
\hline 2000 & 1.1 & ' & 1 & \\
\hline 2500 & 1.1 & ' & 1 & \\
\hline 2800 & 2.0 & ' & 1 & \\
\hline 3000 & 3.0 & ' & 2 & \\
\hline 3300 & 5.1 & ' & 2 & \\
\hline 3500 & 7.1 & ' & 2 & \\
\hline 4000 & 14.6 & ' & 3 & \\
\hline 4500 & 22.3 & ' & 3 & \\
\hline 5000 & 28.7 & ' & 3 & \\
\hline
\end{tabular}

\section*{Table noise input source}

It is possible to provide Eldo some input noise source values depending on the frequency via the table keyword. Eldo accepts the following:
```

Ixx P1 P2 NOISE TABLE [DEC|LOG|LIN] (f1,val1) (f2,val2)...
Vxx P1 P2 NOISE TABLE [DEC|LOG|LIN] (f1,val1) (f2,val2)...

```

Eldo will assume zero current source or zero voltage source in any mode other than NOISE (that is, for DC, AC, TRAN, and so on).
i
For further details, please refer to the "Independent Voltage Source" on page 310 and also the "Independent Current Source" on page 317.

\section*{.OPTPWL}

\section*{Accuracy by Time Window}
```

.OPTPWL PARAM=((TIME1,VALUE1) (TIME2,VALUE2)...)

+ PARAM=((TIME1,VALUE1)...))

```

The .OPTPWL command allows some precision parameters to be reset during transient simulation for different time windows. <PARAM> can be any one of a number of parameters. Values are given in a piecewise-linear format. . OPTPWL can also be changed in Eldo interactive mode.

\section*{Parameters}
- PARAM

This can be any of the following parameters: eps, reltol, reltrunc, vitol, chetol, hmax, HMIN, ABSTOL, FLUXTOL, NGTOL, OUT_RESOL, ITOL, FREQFFT, PCS, TUNING.

The freqfat value can be applied on the time-domain window only if . OPtFOUR is not active and if there is no digital simulator connected.

In the . OPTPWL command, FREQFFT must be used in place of the keyword FREQSMP which is used in the .OPTION command, that is, FREQFFT in .OPTPWL is equivalent to FREQSMP in . OPTION.

The pCS option can be used in conjunction with the .OPTPWL command to specify the time after which to turn on PCS. This might be useful when the PCS option is used in the case of non-periodic conditions which may even slowdown the simulation a little.

\section*{Example}
```

.OPTPWL RELTOL=(0,1.0e-4) (10n,1.0e-3)
.OPTION RELTOL=1.0e-5

```

In the above example, during DC analysis, the value \(1.0 \mathrm{e}-5\) will be used, and during Transient analysis a value of \(1.0 \mathrm{e}-4\) will be used until \(10 \mathrm{n}, 1.0 \mathrm{e}-3\) will be used thereafter.

> Note
> TIME 1 can be 0 , in such case VALUE is used for DC, and would overwrite the default value or the value given via .OPTION. TIMEx,VALUEx can be parameters set via .PARAM commands. . OPTPWL only works in TRAN.

\section*{(1) Please also refer to ".OPTWIND" on page 777.}

\section*{.OPTWIND}

\section*{Accuracy by Time Window}
```

.OPTWIND PARAM=(TIME1,TIME2,VALUE1) ... (TIME1N,TIME2N,VALUEN)

```

The . OPTWIND command allows some precision parameters to be reset during transient simulation for different time windows. <PARAM> can be any one of a number of parameters. Values are given per window time. . OPTWIND can also be changed in Eldo interactive mode.

\section*{Parameters}
- PARAM

This can be any of the following parameters: eps, reltol, reltrunc, vitol, chetol, hmax, HMIN, ABSTOL, FLUXTOL, NGTOL, OUT_RESOL, ITOL, FREQFFT, PCS, TUNING.

The FREQFFT value can be applied on the time-domain window only if . OPTFOUR is not active and if there is no digital simulator connected.

In the . OPTwIND command, FREQFFT must be used in place of the keyword FREQSMP which is used in the .OPTION command, that is, FREQFFT in .OPTWIND is equivalent to FREQSMP in . OPTION.

The pCs option can be used in conjunction with the .OPTWIND command to specify the time after which to turn on PCS. This might be useful when the PCS option is used in the case of non-periodic conditions which may even slowdown the simulation a little.

\section*{Example}
\[
\begin{aligned}
& . \text { OPTWIND RELTOL }=(0,10 \mathrm{n}, 1.0 \mathrm{e}-4) \quad(100 \mathrm{n}, 200 \mathrm{n}, 1.0 \mathrm{e}-3) \\
& . \text { OPTION RELTOL }=1.0 \mathrm{e}-5
\end{aligned}
\]

In this example, during DC analysis, the value \(1.0 \mathrm{e}-4\) will be used, and during Transient analysis a value of \(1.0 \mathrm{e}-4\) will be used until 10 n , then the default value will be used until 100 n (that is, \(1.0 \mathrm{e}-5\) ), \(1.0 \mathrm{e}-3\) will be used between 100 n and 200 n , and \(1.0 \mathrm{e}-5\) again after 200 n .

\section*{Note}

TIME 1 can be 0 , in such case VALUE is used for DC, and would overwrite the default value or the value given via . OPTION. TIMEx, VALUEx can be parameters set via .PARAM commands. For . OPTwind command only, the very last specification can be: (<TIME>, , <VALUE>) which means that after time <TIME>, the parameter value will be equal to <VALUE>. .OPTWIND only works in TRAN.

\section*{(1) Please also refer to ".OPTPWL" on page 776.}

\section*{.PARAM}

\section*{Global Declarations}

\section*{Simple Description}
. PARAM PAR=VAL \(\{P A R=V A L\}\)

\section*{Algebraic Description}
. PARAM PAR=EXPR \(\{P A R=E X P R\}\)

\section*{Assigning a Character String}
.PARAM PAR="NAME"

\section*{User Defined Function}
```

    . \(\operatorname{PARAM} \operatorname{PAR}(\mathrm{a}, \mathrm{b})=E X P R\)
    ```

\section*{Monte Carlo Analysis Parameters}
```

.PARAM PAR=VAL|PAR=EXPR

+ LOT|DEV[/GAUSS|/UNIFORM|/USERDIST]=VAL|(dtype,-3sig,+3sig
+ [,bi,-dz,+dz [,off,sv] [,scale])
.PARAM PAR=VAL LOTGROUP=my_lot_group
.PARAM PAR=MC_DISTRIBUTION
.PARAM PAR=VAL DEVX=VAL

```
. PARAM is used to assign values to parameter variables used in model and device instantiation statements. Parameters and expressions may be used in all of the following cases, for definition and value updating of:
- Device and Model Values.
- Independent Voltage and Current Source Values.
- Linear, Polynomial Coefficients, and Arithmetic Expressions (E \& G only) in Dependent Sources.
- Terms used in .DEFMAC, .DEFWAVE and .extract statements.
- Monte Carlo analysis distribution.

Multiple parameters can be set in a single .PARAM command and any combination of parameter types above may be used. There is no limit to the number of parameters that can be set.
.DC and . STEP statements may be used to define any parameter in the main circuit.

\section*{Note}

Parameters and expressions are not allowed in device names and nodes. In commands they are only allowed if explicitly specified in the documentation. Only one definition per parameter is allowed.

If a parameter is specified more than once in a netlist, Eldo will by default use the last value specified. This includes instances that are specified earlier than the last .PARAM specification. Specify option usefirstdef to force Eldo to only use the first definition (any further definitions are ignored). For example, if a netlist includes:
```

.param res=10
r1 4 2 'res'
.param res=13

```
then r1 will take the value 13 . With option usefirstdef specified, Eldo will only use the first definition, so r1 will take the value 10 .

The .PARAM command is order dependent in that all components of any arithmetic expressions used must have been defined earlier in the netlist.

Note


If a parameter \(\mathbf{P}\) is referred to in a netlist but not defined, Eldo searches for \(\mathbf{P}\) in the . Lib files. Only global .PARAM definitions are considered. Parameter declarations within a . subckт definition will not be considered outside that subcircuit. The цот and DEV specifications affect only the parameter before them.

Expressions can be used in a netlist with certain restrictions. These expressions must be contained within braces \(\}\). Constants and parameters may be used in expressions, together with the built-in functions and operators.

Table 10-21 lists reserved keywords which must never appear in a . PARAM command. For example, the following statement generates an error:
.PARAM SCALE=VAL

Table 10-21. Reserved Keywords Never Available in .PARAM
\begin{tabular}{|l|l|l|l|l|}
\hline DCM & FREQ & SCALE & TEMP & TIME \\
\hline TEMPER & XAXIS & & & \\
\hline
\end{tabular}

Table 10-22 lists reserved keywords which cannot be specified in a . PARAM command if an RF analysis is specified in the netlist. If an RF analysis is specified in the netlist, and if any .PARAM command includes one of these reserved keywords, the command will be rejected and an error message given.

Table 10-22. Reserved Keywords Not Available in .PARAM if an RF Analysis is Specified in the Netlist
\begin{tabular}{|l|l|l|l|l|}
\hline BFACTOR & BOPT & B_OPT & FUND_OSC & FUND_OSC<n>1 \\
\hline GA & GA_mag & GA_dB & GAC & GAM \\
\hline GAM_mag & GAM_dB & GAMMA_OPT & GAMMA_OPT_MAG & GASM \\
\hline
\end{tabular}

Table 10-22. Reserved Keywords Not Available in .PARAM if an RF Analysis is Specified in the Netlist
\begin{tabular}{|l|l|l|l|l|}
\hline GASM_mag & GASM_dB & GAUM & GAUM_mag & GAUM_dB \\
\hline GOPT & GP & GP_mag & GP_dB & GPC \\
\hline HERTZ \(^{2}\) & INOISE & KFACTOR & LSC & LT_JITTER \\
\hline MUFACTOR & MUFACTOR_L & MUFACTOR_S & NFMIN & NFMIN_mag \\
\hline NFMIN_dB & ONOISE & PHI_OPT & RNEQ & SNF \\
\hline SNF_mag & SNF_dB & SSC & SSTSNF & TGP \\
\hline TGP_mag & TGP_dB & TNOM \({ }^{3}\) & YOPT & Y_OPT \\
\hline
\end{tabular}
1. Where \(<\mathrm{n}>\) is a number.
2. HERTZ is only unavailable when running in -compat mode.
3. TNOM may be specified as a parameter in a .PARAM command when . OPTION DEFPTNOM
is set. The temperature value used by the Eldo model evaluator is always that which is set with
. OPTION TNOM=VAL. TNOM can also be specified when running in -compat mode.

\section*{Parameters}
- \(\quad\) PAR=VAL

Name and value of the parameter.
- \(\quad\) PAR=EXPR

Name of the parameter and regular arithmetic expression describing it. This expression may use parameter names already defined in the netlist, unless LOT or DEV are specified. Waves must not be part of the expression as the expression is evaluated prior to the simulation. The parameters can also depend on V or I.

For a list of the available arithmetic functions refer to "Arithmetic Functions" on page 78.
- PAR="NAME"

Assigns a character string to the parameter. May be used to parametrize models and subcircuits. Eldo accepts quoted character strings as parameter values. These string values may be used for model names and filenames. To use a string as a parameter, enclose the string within double quotes. To maintain the case of the string enclose the string within double quotes first and then enclose within single quotes.

The value of the string is retrieved simply by specifying the dollar sign (\$) and parentheses ().

See "String Parameters" on page 71 for more information.
- \(\operatorname{PAR}(a, b)=E X P R\)

Specifies a user-defined function in order to define a parameter using an expression. The parameter may then be called when required, for example:
```

            .param P (a,b)=expression
            R1 1 2 'P(a,b)'
    - PAR=VAL PAR=EXPR
+ LOT|DEV[/GAUSS |/UNIFORM|/USERDIST]=VAL |
+ (dtype,-3sig,+3sig
+ [,bi,-dz,+dz [,off,sv] [,scale]])

```

This parameter setting can only be used with a Monte Carlo analysis. For more information see ".MC" on page 706.
```

LOT | DEV=VAL

```

Specifies a Lot or Dev tolerance value of val to the parameter for MC analysis. Lот causes devices to vary with each other. Dev causes devices to vary independently of each other. May be used in combination with GAUSS, UNIFORM or uSERDIST which specify Gaussian, uniform or user-defined distributions respectively. VAL may be specified as a percentage using the \% sign, or as an absolute value. Parametric expressions are allowed in the value of VAL, but not in the parameter defined after a .PARAM statement. LOT and DEV do not allow other parameters to be specified within parameters.
For more information on Lот and DEv, see "Tolerance Setting Using DEV, DEVX or LOT" on page 711.
```

LOT/GAUSS=VAL | DEV/GAUSS=VAL

```

Specifies a Gaussian distribution of random numbers between 46 . VAL specifies the standard deviation of the distribution around the nominal value.
```

LOT/UNIFORM=VAL | DEV/UNIFORM=VAL

```

Specifies a Uniform distribution of random numbers between \(\sigma\). VAL specifies the standard deviation of the distribution around the nominal value.
```

LOT/USERDIST=VAL |EV/USERDIST=VAL

```

Specifies a user-defined distribution of random numbers between \(\sigma\). VAL specifies the standard deviation of the distribution around the nominal value.

See "Assign Nominal Parameter Values" on page 1211.
Different entities are able to share the same distribution. Anywhere Eldo accepts LOT/DEV specifications, you can specify LOTGROUP=group_name.
If no distribution type is specified it will default to UNIFORM. For more information on user defined distributions see ".DISTRIB" on page 614.
```

dtype

```
nor for gaussian distribution.
uni for uniform distribution.
-3sig
Lower 3 sigma bounds with respect to nominal value, this can be specified as a percentage or an absolute value.
```

+3sig
Upper 3 sigma bounds with respect to nominal value, this can be specified as a
percentage or an absolute value.
bi
An optional pair of characters specifying that the distribution is bimodal.
$-\mathrm{dz}$
Lower limit of the "dead zone" in bimodal distribution, this can be specified as a
percentage or an absolute value.
$+\mathrm{dz}$
Upper limit of the "dead zone" in bimodal distribution, this can be specified as a
percentage or an absolute value.
off
An optional offset.
sv
A percentage or absolute value that moves the nominal value of a parameter either
above or below the "typical" nominal value for that parameter.
scale
Specifies whether the calculations are to be held in $\log$ or linear scale. The two options are lin or log.

```

\section*{Note}
```

1. The limits for this syntax for Accusim are -3 sig, 3 sig compared to those of Eldo which are -4 sig, 4 sig.
2. The minus sign in the values -3 sig and -dz is only to specify that they are to the left of the nominal value. Eldo also accepts them as positive values.
3. sv can be $>0$ which means a shift to the right, or $<0$ which means a shift to the left.
```
- LOTGROUP=my_lot_group

Different entities are able to share the same distribution. Anywhere Eldo accepts Lot/Dev specifications, you can specify LOTGROUP=my_lot_group. Please refer to ".LOTGROUP" on page 701 for more information.
- PAR=MC_DISTRIBUTION

When using a Monte Carlo analysis the same random variable will be used each time a parameter affects a model parameter (цот variation). When a declared parameter affects an instance parameter a new random variable is calculated each time it is specified (DEV variation).

\section*{Note}

It is possible to specify that DEv variation will be used for both model and instance parameters, as was default in Eldo versions prior to v6.3_2, by specifying option podev. See "PODEV" on page 982 for more information.

A Monte Carlo distribution can be used to specify how the random variables should be distributed between its upper and lower limits. For more information on Monte Carlo analysis, see "Monte Carlo Analysis" on page 1207.
MC_DISTRIBUTION should be replaced with one of the following keyword statements:
```

UNIF(nominal,relative_variation, [mult])

```

Defines a uniform distribution. PAR can vary between
nominal - nominal*relative_variation and
nominal + nominal*relative_variation.
AUNIF (nominal, absolute_variation, [mult])
Defines a uniform distribution. PAR can vary between
nominal - absolute_variation and nominal + absolute_variation.
GAUSS (nominal, relative_variation, sigcoef, [mult])
Defines Gaussian distribution. The standard deviation is equal to
relative_variation*nominal/sigcoef.
AGAUSS (nominal, absolute_variation,sigcoef, [mult])
Defines Gaussian distribution. The standard deviation is equal to absolute_variation/sigcoef.

\section*{Note}

The following two distribution statements are equivalent:
. PARAM P1=AGAUSS \((2,0.3,3)\)
.PARAM P1=AGAUSS \((2,0.6,6)\)
In both cases, the standard deviation will be 0.1.

\section*{LIMIT (nominal, absolute_variation)}

Outputs PAR - absolute_variation or PAR + absolute_variation depending on whether the random number, varying between -1 and 1 , is negative or positive.
```

nominal

```

The nominal value.
absolute_variation
Absolute value for variation of the nominal value.
relative_variation
Relative value for variation of the nominal value.
```

sigcoef

```

Normalization coefficient.
mult
A positive integer value that acts as a multiplier to set how many times the parameter value is to be calculated. If it is greater than one then the distribution will be bimodal. The result could be either greater or lesser than the nominal value. The result with the largest deviation is then used. If mult is not specified it will default to 1 .

\section*{Note}
Note
Parameter values can be specified with the percentage sign \%. For example, the following
two lines of syntax are equivalent:
.param rgauss=gauss \((2,20 \%, 1)\)
.param rgauss=gauss \((2,0.2,1)\)
- DEVX=VAL

The devx specification forces Eldo to use a new random value for each instance of a subcircuit. The difference with DEv is that even if a parameter is used several times in the same subcircuit, only one value will be used for that particular instance.

\section*{Note}
devx can only be applied on . PARAM, unlike Lot and Dev which can be applied on both model parameters and . PARAM statements.

Note
It is impossible to have DEV and DEvX specified for the same parameter. If DEV and DEvX are specified for the same parameter, the last specification will be retained.

\section*{Related Options}

PARAM_BEFORE_USE (see "PARAM_BEFORE_USE[=0|1]" on page 956), USEFIRSTDEF (see "USEFIRSTDEF" on page 962)

\section*{Examples}

The following example shows how component values may be defined globally using the . PARAM command. Note that Lot and Dev values of \(5 \%\) and \(10 \%\) are also assigned to the parameter lval or MC analysis.
```

r1 1 2 rval
c1 1 2 cval
11 1 2 lval
.param rval=2k cval=3p lval=2u lot=5% dev=10%

```

The following shows how parameters in a .model definition may be assigned symbols which are then declared globally using the .PARAM command.
```

.model mod1 nmos level=3 vto=vtodef
*main circuit
m1 1 2 3 4 modl w=wdef l=ldef
.param vtodef=1 wdef=20u ldef=3u

```

The following shows arithmetic expressions and previously defined parameters combined in a .PARAM command.
```

r1 1 2 p2
.param p1=1k p3=2*p1
.param p2=sqrt(p1)+3*p3

```

The following example shows how parameters may be assigned symbols in a . suвскт definition. The parameters may then be given values explicitly when the subcircuit is called or globally using the .PARAM command.
```

*SUBCKT definition
.subckt inv 1 2
r1 1 3 rval
r2 3 4 rval1
r3 4 2 rval2
.ends inv
*subcircuit call
x1 1 2 inv rval=3 rval2=10
.param rval1=2

```

In the next example, the model name is substituted by the parameter pmod.
```

.param pmod="pmos1"
m1 d g s b \$(pmod) w=1u l=1u

```

The following two examples show how string parameters are used.
```

.param MOD="Pmos1"
m1 d g s b $(MOD) w=1u l=1u
.param STIMFILE='"Stim.txt"'
v1 1 0 pwl file=$(STIMFILE) R

```

The following example shows LOT and DEV specifications, defined for the .param and .model commands:
```

.param p1=10k lot=(UNI,-5%,4%, bi, 3%, 4%)
.model QND NPN BF=100 dev=(NOR,5%,5%,bi,-2%,2%, off, 1%)

```

The following example shows how a user-defined function can be specified. In this case, the value produced for R 1 would be 6 ohms.
```

.param rval (a,b)=a+b
R1 1 2 'rval (2,4)'

```

In the next example the \(\operatorname{Devx}\) declaration, placed on parameter pc , indicates that during a Monte Carlo analysis, a new value of pc has to be randomly generated for x 1 , and another one has to be generated for x 2 :
```

. param $p c=10 \mathrm{p}$ DEVX=10\%
.SUBCKT cmod a b
C1 a b pc
C2 a b pc
.ENDS
x1 40 cmod 10p
X2 68 cmod 10p

```
\(\mathrm{X} 1 . \mathrm{C} 1\) and \(\mathrm{x} 1 . \mathrm{C} 2\) will use the same value (same for \(\mathrm{X} 2 . \mathrm{C} 1\) and \(\mathrm{x} 2 . \mathrm{C} 2\) ).
```

v1 1 0 dc 1 pwl (0 1 10n 9)
r1 1 0 1
v2 2 0 dc 1

```
```

r2 2 3 r={p2} tc1=4.2
r3 3 0 1
.param p1=v(1)
.param p2=2*p1
.tran 1n 10n
.extract tran yval(v(3),4n)
.plot tran v(3)
.end

```

This example shows how parameter p 1 can depend on the voltage at \(\mathrm{v}(1)\).
The following example will return the linearly interpolated value of p 2 ( y value) at an x value of p1.
```

.param p1=1
.param p2=pwl(p1, 1, 0, 10, 0.5, 20, 1.5 ,30)

```

The value of p 2 will be 25 , because the linear interpolation between the 2 nd and 3 rd pairs of values gives 25 .

If linear interpolation was not specified, then \(\mathrm{p} 2=20\). For more information, please refer to "PWL(xvalue, interp, x1, y1, ... xn, yn)" on page 79.

The following example shows Lот and Dev variation usage on MC distribution parameters.
```

.PARAM p1=UNIF (1,0.05)
.MODEL MOD1 NMOS VTO='1*p1'
.MODEL MOD2 PMOS VTO='-1*p1'
M1 ... W='p1*1u'
M2 ... W='p1*1u'

```

The same random value (цот variation) will be used for the calculation of vто for both nмos and pmos models, since in this case p1 is affecting model parameters. However independent random values (Dev variation) will be used for the MOS instances m1 and m2, since p1 is affecting an instance parameter. Use option podev for backward compatibility for the mechanism in versions of Eldo prior to v6.3_2 where DEv variation was used for both model and instance parameters.

\section*{-compat flag}

In -compat mode, Lот and DEv are not considered as keywords, however Lot/GAUSS, DEV/GAUSS, LOT/<distrib_name>, and DEV/<distrib_name> are.

In -compat mode, double quotes are considered as single quotes. (In standard Eldo mode, double quotes are used to specify a parameter string.) Use option qUOTSTR to consider double quotes as a parameter string delimiter.

In -compat mode, Eldo will check whether there is a .model with the same name as the string after the nodes in a model declaration. If not, it will look for a parameter name. This can be confusing, because if there are both a .model and a parameter name with the same name, then
the simulator will consider the string to be a model name, while a parameter name was desired. This can be overcome by placing the parameter name in single quotes in the instantiation.
(1) Please refer to "HSPICE Compatibility" on page 1373 for further information on the -compat flag.

In this example a parameter, rmin, is required as the value of a resistor instantiation. It is placed in single quotes so that it is viewed as a parameter and not a model name.
```

.model rmin fmax=3 nonoise
.param rmin=2k
r1 3 2 'rmin'

```

\section*{.PARAMDEX}

\section*{Statistical Parameter Declarations}

\section*{Noise Factors}
\begin{tabular}{llll}
. PARAMDEX & FACTOR_NAME & [NOISE/] & SIG=NSIGMA \\
.PARAMDEX FACTOR_NAME & [NOISE/] & RNG=NRANGE \\
.PARAMDEX FACTOR_NAME & [NOISE/] & ABS=DELTA \\
.PARAMDEX FACTOR_NAME & [NOISE/] & REL=DELTA\%
\end{tabular}

\section*{Designable Factors}
```

.PARAMDEX FACTOR_NAME [CTRL/] ABS=DELTA [,NOM=RVALUE]
.PARAMDEX FACTOR_NAME [CTRL/] REL=DELTA% [,NOM=RVALUE]

```

Used to assign values to parameters (factors) used in design of experiments. The designer's selection of factors is accomplished by adding minor modifications to the working netlist, using the . PARAMDEX command.

A factor is a circuit parameter that is studied in the experiment. In order to study the effect of a factor on one or several user-defined responses, two or more values of the factor are used. These values are referred to as levels or settings. A combination of factor levels is called a run and will be associated to a specific simulation run in Eldo.

(i)
For the complete description, see the separate chapter Statistical Experimental Design and Analysis.

\section*{.PARAMOPT}

\section*{Optimization Parameter Declarations}
```

.PARAMOPT VARIABLE_NAME=(

+ [INIT_VALUE,]
+ {LOWER_BOUND LOWER_PERCENT% },
+ {UPPER_BOUND UPPER_PERCENT% }
+ [, INCREMENT])

```

The specification of the optimization variables is realized with this extension of the .PARAM command.
(1) For the complete description of optimization capabilities, see the separate chapter
Optimizer in Eldo.

\section*{.PART}

\section*{Circuit Partitioning}
.PART ADIT|ELDO|MODSST
+ INST=(<instance_list>) SUBCKT=(<subcircuit_list>)
The .PART command instructs Eldo to use the specified algorithm in place of the regular transient algorithm, for a certain selection of instances. This performs circuit partitioning.

The instances to be simulated with the specified algorithm may be listed explicitly, using the <instance_list>. They may also be implicitly designated, using the <subcircuit_list>.

\section*{Parameters}

The list below details how Eldo will partition the circuit, the keyword specified selects a simulation algorithm for the according instances/subcircuits:
- ADIT

Use the ADiT algorithm.
- eldo

Use the Eldo algorithm.
- modsst

Use the Eldo RF MODSST algorithm. For further details, see .MODSST (Modulated Steady-State analysis) of the Eldo RF User's Manual.
- <instance_list>

This is enclosed in parenthesis, and contains a list of instance names, separated by commas, possibly using wildcards (* and ?) in place of characters.
- <subcircuit_list>

This is enclosed in parenthesis, and contains a list of subcircuit names separated by commas. Subcircuit names may also contain wildcard characters (* and ?). If a subcircuit appears in the <subcircuit_list>, all instances of this subcircuit will be handled with the specified algorithm.

\section*{Example}

Using these directives will have an effect on how and where simulation occurs, for example:
```

.part ADIT SUBCKT= (NOR1, NAND3, AOIX*)
.part ADIT INST=(XA1.XM2)
.part ELDO INST=(XAMP.XAGC)
.part MODSST SUBCKT=(INV_SPICE)

```

\section*{.PLOT}

\section*{Plotting of Simulation Results}
```

.PLOT [ANALYSIS] OVN [(LOW, HIGH)] [(VERSUS)]

+ {OVN [(LOW, HIGH)]} [UNIT=NAME] [(SCATTERED)] [STEP=value]
.PLOT AC|FSST S(i, j) [(SMITH[,zref])] [(POLAR)]
.PLOT FOUR FOURxx(label_name) [(SPECTRAL)] [(CONTINUOUS)]
.PLOT DSP DSPxx(label_name)
.PLOT EXTRACT [MEAS (meas_name) | SWEEP (sweep_name)]
.PLOT [CONTOUR] MEAS (meas_name_x) MEAS (meas_name_y) [(SCATTERED)]
+ [(SMITH[,zref])] [(POLAR)]
.PLOT [ANALYSIS] TWO_PORT_PARAM [(SMITH[,zref])] [(POLAR)]

```

The . Рцот command takes its name from Berkeley SPICE (2G6). It is used to specify which simulation results have to be kept by the simulator for graphical viewing and post-processing. For the first syntax above, at least one ovn (output variable name) plot specification is required to plot values of specific nodes or components. See "Plot Specifications (OVN)" on page 799.

See full list of "Parameters" on page 796.

\section*{Files created by .PLOT Commands}

The quantities listed in a . Рцот command are written to binary output files (.wdb). The binary files are the input data for the EZwave waveform viewer compatible with Eldo. Saved windows files .swd are created with a.\(w d b\) database and contain information on specific graph windows such as size or position. They also contain the waveforms associated with graph windows. When specifying plots for frequency based analysis, the . swd file contains the information for complex waveforms, which can then be viewed by opening the .swd file with EZwave.

\section*{Note}


Specify option nowavecomplex (see "NOWAVECOMPLEX" on page 1005) to force complex waveform information to be stored within the waveform database (. \(w d b\) ) as well as the .swd file. This restores the functionality of Eldo versions prior to v6.3_2.1.

By default, the quantities listed in a . РLот command are not written to the main ASCII output file (.chi), see "ASCII Outputs in the .chi File" on page 795.

\section*{Types of Waveforms}

Many different simulation results can be created by Eldo. The simulator can output simple node voltages, but also currents through devices, currents through device or subcircuit pins, power quantities, S parameters, internal variables from device models, and so on. All these results are direct raw results from a simulation. The tables shown in the next few pages indicate the exact syntax to use for each category. Example:
```

.PLOT TRAN V(OUT)
.PLOT DC ISUB(XBIAS.VOUT)

```

The . Рцот command may also be used to plot extraction results. A flexible language exists in Eldo to extract characteristics from raw simulation results (for example the maximum value of a waveform, or the time at which a given threshold is crossed by a waveform, and so on). See ".EXTRACT" on page 637.

When extraction statements are combined with parameter sweeping statements (see ".STEP" on page 890), Eldo automatically creates waveforms showing the extraction results versus the swept parameter. For example, a user may extract the width of an output pulse from a transient simulation, and sweep the power supply level. In this case Eldo will automatically create a waveform showing the width of the pulse versus the power supply level. Similarly, if extractions and .ALTER statements are combined, Eldo will automatically create waveforms showing the extraction results versus the index of the .ALTER runs (see ".ALTER" on page 549 ). In this case, the \(X\) axis will contain \(1,2,3\), and so on. The initial display in the viewer can also be prepared using .Рцот commands (see the .РLOт ехтRACT... description, "EXTRACT" on page 798). Example:
```

.EXTRACT TRAN label=VMAX MAX(V(out))
.PARAM powersupply=1.2
VDD VDD O 'powersupply'
.STEP PARAM powersupply list 1.2V 1.3V 1.4V 1.6 2V
.PLOT EXTRACT meas(VMAX) ! this will create a waveform
showing VMAX(powersupply)

```

By default, using the.\(w d b\) format, the . Extract waveforms are saved inside the \(E X T\) folder in the main.\(w d b\) file. Specify option extrile enables the generation of a .ext.wdb file with only the extraction results.

If using the .cou format, these .ехтRACT waveforms are created in a separate file with the .ext extension. The command-line switch -couext (eldo -couext -i <netlist.cir>) can be used to merge the extract waveforms into the .cou file, when possible. In this case, a single .cou file will contain the raw waveforms and also the extraction waveforms.

Finally, the . РLOT command, combined with the .DEFWAVE command (see ".DEFWAVE" on page 605) can also be used to generate so-called template waveforms, that is. piece-wise-linear waveforms defined by a series of arbitrary ( \(\mathrm{x}, \mathrm{y}\) ) coordinates. Using . РLOт, these templates can be displayed together with the simulation results (this is very useful when verifying whether a filter response passes or not specifications such as cutoff frequencies, minimum attenuation and so on). Example:
```

.DEFWAVE FILTERSPEC=PWL(1e-3,0,100k,0,500k,-60,100G,-60)
.PLOT AC VDB(OUT) W(FILTERSPEC)

```

\section*{Complex Modifiers and Initial Formatting}

Some results are real quantities, such as the currents and voltages from a transient analysis, while others are complex. In this case, real or imaginary parts, magnitude or phase or group delay, can be required by the user.

It is also possible to specify some initial basic formatting of the results. For example, spectral or scattered display modes can be specified, instead of the default continuous-line mode. S, Y, Z parameters can be automatically displayed in a Smith chart, and so on. These optional specifications do not alter the raw data, they only tell the waveform viewer how to display the data initially.

\section*{X axis of Waveforms}

In general, the created waveforms have their X axis implicitly defined by the corresponding analysis. For example, the X axis of a transient waveform is the time, the X axis of an AC waveform is the frequency and so on. The X axis for a transient waveform is defined by the . TRAN command, it ranges from \(t=0\) to \(t=t m a x\) where tmax is specified in the .TRAN tstep tmax command (see ".TRAN" on page 911). The X axis for an AC waveform is defined by the frequency points in the .AC command (see ".AC" on page 538). DC and NOISE waveforms also inherit their X axis from the corresponding analysis command (.DC or .NOISE).

For all analyses but the transient analysis, the X -axis range and the spacing of points in the X axis are thus predictable. For example, the frequency points in a .AC command are either listed explicitly or regularly spaced, in a predictable way. For transient analysis however, this is different. Eldo always uses a variable timestep algorithm, and the spacing of the timepoints where the circuit is solved is dictated by accuracy considerations only (see the Speed and Accuracy chapter). Thus the total number of timepoints is generally not predictable. By default, all computed timepoints are stored in the binary output files, so that any rapid change or glitch can be inspected visually in the waveform processor. However, when working with large circuits and/or long transient simulations and/or storing many waveforms, this may generate huge output files. The loading and post-processing of these huge output files by the waveform viewers may thus be slower. In extreme cases, this may also impact the simulation time, as writing gigabytes to a disk, possibly through a busy network, may take quite a while. The next section discusses several options meant to control the size of the transient output files.

In the case of . .extract waveforms, the X axis is defined by the parameter sweeping statement (. STEP), or it contains integer indexes (. ALTER).

\section*{Limiting the Size of Transient Output Files}

At least three options are available in Eldo to limit the size of the output files for transient simulation. The first one is the option out_step=val, the second one is option
OUt_RESOL=resolution, and the third one is option INTERP=1. Of course, the many options related to the accuracy settings do generally have an impact upon the number of computed points and thus upon the size of the output files, but this is only qualitative and indirect. There is no way to quantitatively relate, say the eps or the reltol specification, to the final size of the output files-this all depends on the circuit. In contrast, the options discussed in this section allow controlling the amount of data in a predictable way (the out_resol option only sets a maximum size, whereas out_Step and interp allow exact predictions). These options may have a considerable impact on the overall simulation speed, so it is important to define exactly what has to be achieved.
- Option out_Step

The . OPtIon out_step=val command (see "OUT_STEP" on page 1006) forces a timepoint at each multiple of val, and only these timepoints are stored in the binary output files. These timepoints are forced, that is, they come in addition to the normal timepoints picked by the simulator. When using this option, the timepoints are forced, that is, they are computed even if they are not required from an accuracy point of view. One of the applications of the out_STEP option is for FFT computations. In this case, it is frequent that the user wants to have exact, computed points, at regularly spaced timepoints, to minimize the interpolation artifacts when computing an FFT. However the out_STEP option is also a way to control the size of the output files, even if no FFT is scheduled. If not chosen properly, a possible risk of the out_Step option is to slowdown the simulation unnecessarily, by forcing Eldo to compute more points than needed. This is particularly true if they are long periods of time with little or no activity in the simulation. Forcing a short out_step will force many useless timepoints during these periods, whereas Eldo would normally accelerate and compute fewer timepoints. This option is however preferred by some users because the output waveforms ultimately contain only computed points, without interpolation.
- Option out_resol

Another option used to reduce the size of the output file is the out_resol option. With this option, the user can specify the smallest resolution of the output file (see "OUT_RESOL=VAL" on page 1006). Computed data is then dumped only if the current time is greater than the previously written timepoint, augmented by the resolution. For example if out_resol is set to 1 ns , and the simulator has written data at time \(\mathrm{t}=24.65 \mathrm{~ns}\), all timepoints computed until \(\mathrm{t}=25.65 \mathrm{~ns}\) will not be dumped. The first timepoint after \(t=25.65 \mathrm{~ns}\) will be dumped. This could be \(\mathrm{t}=25.76 \mathrm{~ns}\) for example, or \(\mathrm{t}=27 \mathrm{~ns}\) if the simulator can accelerate in this period of time. No timepoints are forced other than those naturally picked by the simulator. Thus the spacing of timepoints in the output file is generally non-constant. The maximum average density of timepoints in the output file is determined by the resolution parameter of the option. The minimum density is not guaranteed, neither locally, nor globally. This option is an interesting alternative, combining the certainty that the points in the output are computed points only (no interpolation error), and the ability to handle low activity periods efficiently. It is however, generally not well suited for simulations where an FFT must be computed, because of the non-constant spacing of the timepoints (this would result in interpolation errors when re-sampling for the FFT).
- Option interp

Both out_step and out_resol options dump only computed points to the output file. Sometimes it may be desirable to obtain equally spaced time points, but forcing timepoints (with out_Step for example) would result in an unacceptable CPU penalty. In these cases, interpolating may be useful. An interpolation option is available to force Eldo to sample the output data along the <tstep> parameter of the .TRAN command (see ".TRAN" on page 911). If using the option INTERP=1 (see "INTERP" on
page 978), the transient output waveforms are interpolated, and the timepoints written to the file are aligned with multiples of <tstep> exactly. For example, if using both the following:
```

.tran 1ns 100ns
.option interp=1

```
the output waveforms will contain exactly 101 points (time 0 is always included), spaced by 1 ns . Glitches shorter than 1 ns may not be caught in the resulting waveform. This is a radical way to reduce the size of the binary output files (.wdb). However, the written data is obtained by interpolation, thus including an unpredictable amount of interpolation error. During low-activity periods, Eldo still picks the largest possible timesteps which will still allow to meet the accuracy requirements, and fills the output data with interpolated data (at no or little cost, as opposed to the our_Ster technique discussed previously).

\section*{ASCII Outputs in the .chi File}

By default, the quantities listed in a . PLOT command are not written to the ASCII .chi output file. This avoids creating huge .chi output files in the case of large simulations. The ASCII outputs are still supported for SPICE compatibility reasons, although seldom used. To force Eldo to generate these output quantities in the ASCII output file, specify the -ascii command-line flag when invoking Eldo or include the option ASCII in the netlist (see "ASCII" on page 998). Symbols such as *, +, and so on, will be used to identify each quantity, to create ASCII waveforms in the .chi output file.

\section*{Note}

For transient results, the spacing of these points in the ASCII waveforms is defined by the <tstep> parameter of the .TRAN command (data is interpolated). This is for original SPICE compatibility. For all other analyses, the points in the X axis are those specified by the corresponding analysis command.

\section*{Wildcards}

You can include wildcards in .Рцот commands. See "Using Wildcards in Subcircuit Instances" on page 843 for more information on using wildcards with .PLOT/. PROBE commands.

Waveforms specified in previous . PLOт commands are excluded from the wildcard plot.

\section*{Related Commands}

See the .print and .probe commands.

\section*{Parameters}
- ANALYSIS

Optional. Specifies the analysis type, which can be useful in the case of multiple types of analysis in the .cir file. Can be one of the following:

\section*{DC}

Specifies that the plots are required for a DC analysis.
AC
Specifies that the plots are required for an AC analysis.

\section*{TRAN}

Specifies that the plots are required for a transient analysis.
NOISE
Specifies that the plots are required for a noise analysis.
```

SSTAC|SSTXF|SSTNOISE|SSTJITTER|TMODSST|FMODSST|FOURMODSST|TSST|
FSST|SSTSTABIL

```

Please refer to the Display Command Syntax chapter of the Eldo RF User's Manual for more information regarding these RF options.
```

OPT

```

Extraction during optimization analysis. Can only be used with wave type wort. This wave type is used for optimization analysis only, that is, it may only be used with орт. For more information on wave type wort, see "WOPT" on page 1191.
- FOUR

Displays FFT results. Please see FOURxx (label_name) below for display options.
- DSP

Displays DSP results. Please see DSPxx (label_name) below for display options. See also ".DSP" on page 615.
- ovn

Output variable name. Requests plotting of values of specific nodes on components.
Required. The syntax for specifying the list of plot specifications to be monitored is under "Plot Specifications (OVN)" on page 799.
- FOURxx (label_name)

Should be specified as part of ovn. Displays FFT results. xx stands for DB, M, P, R, I:
dB Magnitude, in dB
m Magnitude
P Phase
R Real part
I Imaginary part
- DSPxx(label_name)

Should be specified as part of ovn. Displays DSP results. xx stands for DB, M, P, R, I, GD (see above), GD is Group Delay.
- LOW, HIGH

The optional plot limits Low and high may be specified for each of the output variables. All output variables of the same kind (voltage for instance) to the left of a pair of plot limits (LOW, HIGH) will be plotted using the same lower and upper bounds. If plot limits are not specified, Eldo uses the following default values:
- 0 V and 5 V for LOW and high values respectively in voltage plots
- -100 dB and 100 dB for Low and high values respectively in dB plots
- -180 and 180 degrees for Low and HIGH values respectively in phase plots
- UNIT=NAME

Displays user-defined text representing the Y-axis units of a plot. Useful in conjunction with the . Defwave command and with Eldo-FAS.
- (versus)

Specifies the waveform viewer plot one, or a number of waves on the Y-axis against a single wave on the X -axis. (versus) must be preceded by at least one wave and followed by one wave only.
- (SCATtERED)

Only computed points will be represented (no "line" between two successive points). This property is active for all waves of the graph.
- Step=value

Performs a sampling of the waveform(s). A point is dumped every value. It can only be specified for databases that support multiple \(x\)-axes in the same simulation, for example JWDB. Other databases will ignore this parameter.
- \(\mathbf{s}(i, j)\)

Smith chart specification of the \(S\) parameter \(S_{i j}\).
- (SMITH[,zref])

Prompts the waveform viewer to display the waves which are given in the corresponding . PLot command in a Smith chart. Waves must be given without any AC extension, otherwise Eldo will issue an error. The SMITH keyword can only be used in conjunction with Smith chart specifications above. zref is optional and specifies the impedance.
- (POLAR)

Prompts the waveform viewer to display the waves which are given in the corresponding . РLот command in a Polar chart.
- (SPECTRAL)

Specifies the waveform viewer to represent the wave in its spectral representation. This is the default for FFT waveforms. This keyword must be placed at the end of the command, and be enclosed in parentheses.
- (CONTINUOUS)

Specifies the waveform viewer to represent the wave in continuous mode instead of the default spectral representation. This keyword must be placed at the end of the command, and be enclosed in parentheses. This modifies the .swd file only; FFT waveforms are still saved in the.\(w d b\) file as spectral. Can be alternatively specified with the option
CONTINUOUS_FFT.
- EXtract

Allows plot combinations in .ext file. This is to be used in conjunction with .ALTER/.STEP/.TEMP to organize extracted waves in graphs. For example, if you have:
```

.EXTRACT LABEL = a <expression>
.EXTRACT LABEL = b <expression>

```
use . PLot extract meas (a) meas (b) if both waves are expected in the same plot on the waveform viewer invocation.
- CONTOUR

Eldo will plot the second measurement value with respect to the first. The wave will be displayed in a Smith chart if keyword SMITH is specified. contour information is written to the .ext file. At least one . Step command is required to use Contour plots.

\section*{Note}
\(\qquad\)
The keyword vect or catvec must have been specified on the .extract which is referred to in the . PLOT contour, otherwise the corresponding data will be reduced to a single print.
The two measurements in the contour must have the same dimension. If not, the .PLOT contour will be ignored.

See the Contours section of the Eldo RF User's Manual for more information on using . PLot Contour.
- TWO_PORT_PARAM

This must be replaced by one of the following keywords:
Table 10-23. Two-port Parameter Keywords
\begin{tabular}{|l|l|l|l|l|}
\hline BFACTOR & BOPT & GA_mag & GA_dB & GAC \\
\hline GAM_mag & GAM_dB & GAMMA_OPT & GAMMA_OPT_MAG & GASM_mag \\
\hline GASM_dB & GAUM_mag & GAUM_dB & GOPT & GP_mag \\
\hline GP_dB & GPC & KFACTOR & LSC & MUFACTOR \\
\hline MUFACTOR_L & MUFACTOR_S & NC & NFMIN_mag & NFMIN_dB \\
\hline PHI_OPT & RNEQ & SSC & TGP_mag & TGP_dB \\
\hline YOPT & & & & \\
\hline
\end{tabular}

\section*{Note}

All of these keywords may appear in expressions. However, they may not be specified in a . PARAM command if an RF analysis is specified in the netlist. These keywords are all available with both AC and FSST results.

\section*{Plot Specifications (OVN)}
- NOISE(element_name)

Should be specified as part of ovn. Specifies that the plots are required for a noise analysis of a specific component or subcircuit instance. Multiple occurrences of this parameter can appear in a single line of syntax.
- INOISE

Should be specified as part of ovn. Input noise when performing a noise analysis.
- onoise

Should be specified as part of ovv. Output noise when performing a noise analysis.

\section*{Note}

NOISE (element_name), INOISE or ONOISE can appear singularly or as part of any combination. It is necessary that at least one be specified.
inoise and onoise may appear in expressions. However, they may not be specified in a . PARAM command.

For more information on the use of inOISE and onoise, see the example in ".NOISE" on page 744 and "ONOISE" on page 813.
- FOURxx (label_name)

Displays FFT results. Should be specified as part of ovn. xx can be Db, m, P, R, I, GD:
DB Magnitude, in dB
m Magnitude
P Phase
R Real part
I Imaginary part
GD Group Delay
- DSPxx(label_name)

Displays DSP results. Should be specified as part of \(O V N . x x\) can be DB, M, P, R, I, GD (see meanings above).
- LSTB_xx

Displays loop stability analysis (LSTB) results. Should be specified as part of ovn. xx can be \(\mathrm{D}, \mathrm{M}, \mathrm{P}, \mathrm{R}, \mathrm{I}, \mathrm{GD}\) (see meanings above).
- VDIG (node_name)

Should be specified as part of ovn. Enables the plotting of an analog signal as a digital bus. See "Plotting an analog signal as a digital bus" on page 823 for further details.
- WXXX(devname.posi)

Should be specified as part of ovn. Returns the value of complex waveforms defined by the .DEFWAVE command or implicit declarations such as w('P(parameter_value)') and W('wave_dependent_expression'). WXxx can be: W, WDB, WP, WR, WI, WM, WGD, or WOPT.
- vxxx(devname.posi)

Should be specified as part of ovn. Returns the voltage on the pin. vxxx can be: vx, vxdb, vXP, VXR, VXI, VXM, or VXGD.
- IXxx(devname.posi)

Should be specified as part of ovn. Returns the current on the pin. IXxx can be: Ix, IxDb, IXP, IXR, IXI, IXM, or IXGD. The current is positive when it enters the object by this pin.
```

devname

```

Device name.
```

posi

```

Position of the pin as given in the .cir file. posi can be greater than the number of external pins. In such a case, internal pin values are given. Internal pins are sorted in the same order as external pins ( 5 on a BJT for instance, refers to the 5th pin, which is the 1st internal pin, which is the internal collector). The case for GUDM models (Mextram, HICUM) is different, because the intrinsic structure of such models is not known to Eldo. The internal pins can be sorted in any order, therefore the value of intrinsic pins for GUDM models can be accessed only by the writer of the model.
- DATA(dataname, parameter)

Should be specified as part of ovn. Allows to plot a wave defined with a .DATA statement. dataname is the name assigned to the .DATA statement. It is mostly used to define fitting waves during optimization.
- IPROBE(vname)

Should be specified as part of ovn. Returns the sum of the currents on the . Iprobe zero voltage source. See ".IPROBE" on page 689.
- IN (nodename)

Should be specified as part of ovn. Expands the command into multiple plot instructions corresponding to the objects connected to that pin. For example:
```

R1 1 2 1
R2 2 0 1
.PLOT tran in(2)

```
the plot specification will expand the plot into two items:
```

.PLOT tran ix(r1.2) ix(r2.1)

```
- INX(Xinstance.index)

Should be specified as part of ovn. Expands the command into multiple plot instructions corresponding to the devices connected to the instance at the specified pin. For example:
```

.SUBCKT foo a b
r1 a b 1
r2 b 0 1
.ends
X1 a b foo
.PLOT TRAN INX(X1.2)

```
the plot specification will expand the plot into two items:
```

.PLOT tran ix(x1.r1.2) ix(x1.r2.1)

```

Note
These two command parameters IN() and INX() can appear in .PLOT, .PROBE, or .PRINT exclusively. This is because In (node) is always 0 , (the sum of the currents flowing onto a pin is 0 ), and if you want to access current entering a subckt by a specific pin, then command IX (instance.index) is already provided and should be used instead of INX().

\section*{Note}

When the -compat flag is set, the following apply:
For R/L/C/E/F/G/H/I/V/D devices, \(\mathbf{I} 2\) returns the same value as \(\mathbf{I} 1\).
For M/B/J devices, \(\mathbf{I} 3\) is positive when current leaves the object by pin number 3 .
- OPMODE (device_name)

Should be specified as part of ovn. Returns the DC working mode of the device model, device_name. Within . PLot/. probe the use of opmode is restricted to JWDB files because this is the only output format supporting enumerated waveforms (the wave OPMODE () is represented as a digital waveform using states linear/saturation/subthreshold, etc.). Eldo plots the DC working mode of a device as a string instead of a real value. Strings returned are:
- for MOS devices:
linear, if \(V G S>V T\) and \(V D S<V D S A T\)
SATURATION, if \(V G S>V T\) and \(V D S>V D S A T\)
subthreshold, if \(V G S<V T\)
- for BJT devices:
saturation, if \(V B E>0\) and \(V B C>0\)
on, if \(V B E>0\) and \(V B C<0\)
OFF, if \(V B E<0\) and \(V B C<0\)
inverse, if \(V B E<0\) and \(V B C>0\)

The following example plots returns the DC working mode of device m 2 in subcircuit instances x 1 and x 2 .
```

.plot tran opmode(x2.m2) opmode(x1.m2)

```

Below is a list of devices and the syntax used to plot or print the values of both their extrinsic and intrinsic pins. The information is divided first by device and then into subsections of output type and analysis type. For devices, if the position number specified is greater than the index available for the device, it will return a value of zero.

The plot specifications must match the corresponding analysis type, AC, DC, TRAN, or NOISE.
i For examples of syntax usage, see the "Examples" on page 823.

The output quantities listed in Table 10-24 are generic for MOSFET models. Some newer models have names that are different than listed here. These are documented with the model, as is the case for the BSIM4 model.

Table 10-24. MOSFET Plotting and Printing
\begin{tabular}{|l|l|}
\hline \multicolumn{2}{|l|}{ DC or Transient Analysis } \\
\hline \multicolumn{2}{|l|}{ Currents } \\
\hline ID(Mxx)/I(Mxx.D)/IX(Mxx.1) & Drain current \\
\hline IG(Mxx)/I(Mxx.G)/IX(Mxx.2) & Gate current \\
\hline IS(Mxx)/I(Mxx.S)/IX(Mxx.3) & Source current \\
\hline IB(Mxx)/I(Mxx.B)/IX(Mxx.4) & Bulk current \\
\hline IBD(Mxx) & Bulk-drain diode current \\
\hline IBS(Mxx) & Bulk-source diode current \\
\hline Voltages & \\
\hline VD(Mxx)/VX(Mxx.1) & Drain voltage, in Volts \\
\hline VG(Mxx)/VX(Mxx.2) & Gate voltage, in Volts \\
\hline VS(Mxx)/VX(Mxx.3) & Source voltage, in Volts \\
\hline VB(Mxx)/VX(Mxx.4) & Bulk voltage, in Volts \\
\hline VGS(Mxx) & Gate-source voltage, in Volts \\
\hline VGB(Mxx) & Gate-bulk voltage, in Volts \\
\hline VDS(Mxx) & Drain-source voltage, in Volts \\
\hline
\end{tabular}

Table 10-24. MOSFET Plotting and Printing
\begin{tabular}{|c|c|}
\hline VBS(Mxx) & Bulk-source voltage, in Volts \\
\hline VBD(Mxx) & Bulk-drain voltage, in Volts \\
\hline VT(Mxx) & Threshold voltage value, in Volts \\
\hline VDSS(Mxx) & Saturation voltage value, in Volts \\
\hline \multicolumn{2}{|l|}{Conductances} \\
\hline GDS(Mxx) & \[
\frac{\partial I_{D}}{\partial V_{D S}}
\] \\
\hline GM(Mxx) & Transconductance: \(\frac{\partial I_{D}}{\partial V_{G S}}\) \\
\hline GMBS(Mxx) & \[
\frac{\partial I_{D}}{\partial V_{B S}}
\] \\
\hline GMIBD(Mxx) & Mosfet diode drain conductances \\
\hline GMIBS(Mxx) & Mosfet diode source conductances \\
\hline \multicolumn{2}{|l|}{Capacitances} \\
\hline CGS(Mxx) & \(\frac{\partial Q G}{\partial V S}\) Gate/Source capacitance \\
\hline CGD(Mxx) & \(\frac{\partial Q G}{\partial V d}\) Gate/Drain capacitance \\
\hline CGG(Mxx) & \(\frac{\partial Q G}{\partial V g}\) Gate/Gate capacitance \\
\hline CGB(Mxx) & \(\frac{\partial Q G}{\partial V b}\) Gate/Bulk capacitance \\
\hline CBS(Mxx) & \(\frac{\partial Q B}{\partial V S}\) Bulk/Source capacitance \\
\hline CBD(Mxx) & \(\frac{\partial Q B}{\partial V d}\) Bulk/Drain capacitance \\
\hline CBG(Mxx) & \(\frac{\partial Q B}{\partial V g}\) Bulk/Gate capacitance \\
\hline
\end{tabular}

Table 10-24. MOSFET Plotting and Printing
\begin{tabular}{|c|c|}
\hline CBB(Mxx) & \(\frac{\partial Q B}{\partial V b}\) Bulk/Bulk capacitance \\
\hline CBSJ(Mxx) & \(\frac{\partial Q B}{\partial V b s}\) Bulk/Source junction diode capacitance \\
\hline CBDJ(Mxx) & \(\frac{\partial Q B}{\partial V b d}\) Bulk/Drain junction diode capacitance \\
\hline CDS(Mxx) & \(\frac{\partial Q D}{\partial V S}\) Drain/Source capacitance \\
\hline CDD(Mxx) & \(\frac{\partial Q D}{\partial V d}\) Drain/Drain capacitance \\
\hline CDG(Mxx) & \(\frac{\partial Q D}{\partial V g}\) Drain/Gate capacitance \\
\hline CDB(Mxx) & \(\frac{\partial Q D}{\partial V b}\) Drain/Bulk capacitance \\
\hline CSS(Mxx) & \(\frac{\partial Q S}{\partial V S}\) Source/Source capacitance \\
\hline CSD (Mxx) & \(\frac{\partial Q S}{\partial V S}\) Source/Drain capacitance \\
\hline CSG(Mxx) & \(\frac{\partial Q S}{\partial V g}\) Source/Gate capacitance \\
\hline CSB(Mxx) & \(\frac{\partial Q S}{\partial V b}\) Source/Bulk capacitance \\
\hline CGDO(Mxx) & Gate/Drain overlap capacitance \\
\hline CGSO(Mxx) & Gate/Source overlap capacitance \\
\hline CGBO(Mxx) & Gate/Bulk overlap capacitance \\
\hline \multicolumn{2}{|l|}{Charges \({ }^{1}\)} \\
\hline QG(Mxx) & Gate charge \\
\hline
\end{tabular}

Table 10-24. MOSFET Plotting and Printing
\begin{tabular}{|c|c|}
\hline QB(Mxx) & Bulk charge \\
\hline QD(Mxx) & Drain charge \\
\hline QS(Mxx) & Source charge \\
\hline QBD (Mxx) & Bulk-drain junction charge \\
\hline QBS(Mxx) & Bulk-source junction charge \\
\hline \multicolumn{2}{|l|}{Power} \\
\hline POW(Mxx) & Power curve calculated as the product of the drain to source voltage and the drain to source current (Vds \(\times \mathrm{Ids}\) ) \\
\hline \multicolumn{2}{|l|}{AC Analysis} \\
\hline \multicolumn{2}{|l|}{Currents \({ }^{2}\)} \\
\hline Izz(Mxx.D) & Drain current. See below for meaning of zz \\
\hline Izz(Mxx.G) & Gate current. See below for meaning of zz \\
\hline Izz(Mxx.S) & Source current. See below for meaning of zz \\
\hline Izz(Mxx.B) & Bulk current. See below for meaning of zz \\
\hline \multicolumn{2}{|l|}{Noise Analysis} \\
\hline IBSNOISE(Mxx) & Base-Source diode noise: shot noise due to IBD \\
\hline IBDNOISE(Mxx) & Base-Drain diode noise: shot noise due to IBS \\
\hline RSNOISE(Mxx) & Source access resistor noise \\
\hline RDNOISE(Mxx) & Drain access resistor noise \\
\hline RGNOISE(Mxx) & Gate access resistor noise (for MOS model with RG resistance) \\
\hline THNOISE(Mxx) & Thermal noise \\
\hline FLKNOISE(Mxx) & Flicker noise \\
\hline \multicolumn{2}{|l|}{Instance Parameters} \\
\hline EVAL(Mxx, Leff) & Effective length \\
\hline EVAL(Mxx, Weff) & Effective width \\
\hline EVAL(Mxx, ADeff) & Effective drain area \\
\hline EVAL(Mxx, ASeff) & Effective source area \\
\hline EVAL(Mxx, PDeff) & Effective drain perimeter \\
\hline EVAL(Mxx, PSeff) & Effective source perimeter \\
\hline EVAL(Mxx, Geo) & The GEO parameter (geometry selector) \\
\hline
\end{tabular}

Table 10-24. MOSFET Plotting and Printing
\begin{tabular}{|l|l|}
\hline EVAL(Mxx, RDeff) & Effective drain series resistance \\
\hline EVAL(Mxx, RSeff) & Effective source series resistance \\
\hline Special Outputs in the .chi File & \\
\hline VTH_D & Vgs - Vth \\
\hline
\end{tabular}
1. Available for charge controlled models only.
2. In the above specifications, zz is to be replaced by one of the following:

DB (Magnitude, in dB); M (Magnitude); P (Phase); R (Real part); I (Imaginary part); GD (Group delay).
Table 10-25. BJT Plotting and Printing
\begin{tabular}{|l|l|}
\hline \multicolumn{2}{|l|}{ DC or Transient Analysis } \\
\hline \multicolumn{2}{|l|}{ Currents } \\
\hline IC(Qxx)/I(Qxx.C)/I(Qxx.1) & Collector current \\
\hline IB(Qxx)/I(Qxx.B)/I(Qxx.2) & Base current \\
\hline IE(Qxx)/I(Qxx.E)/I(Qxx.3) & Emitter current \\
\hline IS(Qxx)/I(Qxx.S)/I(Qxx.4) & Substrate current \\
\hline Voltages & Internal node voltage difference base-emitter \\
\hline VBEI(Qxx) & Internal node voltage difference base-collector \\
\hline VBCI(Qxx) & Internal node voltage difference collector-emitter \\
\hline VCEI(Qxx) & External node voltage difference base-emitter \\
\hline VBE(Qxx) & External node voltage difference base-collector \\
\hline VBC(Qxx) & External node voltage difference collector-emitter \\
\hline VCE(Qxx) & \multicolumn{1}{|l|}{} \\
\hline Conductances & Transconductance: \(\frac{\partial I_{C}}{\partial V_{B E}}\) \\
\hline GM(Qxx) & Base/Substrate capacitance (LPNP only) \\
\hline Capacitances & Extrinsic Base/Substrate capacitance (LPNP only) \\
\hline CBS(Qxx) & Extrinsic Base/Collector capacitance \\
\hline CBSX(Qxx) & Collector/Substrate capacitance \\
\hline CBX(Qxx) & Base/Collector capacitance \\
\hline CCS(Qxx) & Base/Emitter capacitance \\
\hline CMU(Qxx) &
\end{tabular}

Table 10-25. BJT Plotting and Printing
\begin{tabular}{|l|l|}
\hline \multicolumn{2}{|l|}{ Resistances } \\
\hline RO(Qxx) & Resistance between internal nodes C and E \\
\hline RPI(Qxx) & Resistance between internal nodes B and E \\
\hline RX(Qxx) & \begin{tabular}{l} 
Series resistance between internal and external Base nodes \\
(Base Resistance)
\end{tabular} \\
\hline RBB(Qxx)/RX(Qxx) & Base resistance value \\
\hline Power & \begin{tabular}{l} 
Power curve calculated as the product of the collector to emitter \\
voltage and the collector to emitter current (VCE \(\times\) ICE)
\end{tabular} \\
\hline POW(Qxx) & \begin{tabular}{l} 
Frequency at which small-signal forward current transfer ratio \\
extrapolates to unity
\end{tabular} \\
\hline Frequency & \multicolumn{1}{|l|}{} \\
\hline AC Analysis & Collector current. See below for meaning of zz \\
\hline Currents & \\
\hline Izz(Qxx.C) & Base current. See below for meaning of zz \\
\hline Izz(Qxx.B) & Emitter current. See below for meaning of zz \\
\hline Izz(Qxx.E) & Substrate current. See below for meaning of zz \\
\hline Izz(Qxx.S) & Shot IC noise \\
\hline Noise Analysis & Shot IB noise \\
\hline ICNOISE(Qxx) & Thermal noise \\
\hline IBNOISE(Qxx) & Flicker noise \\
\hline THNOISE(Qxx) & Thermal noise due to access resistance RB \\
\hline FLKNOISE(Qxx) & Thermal noise due to access resistance RE noise due to access resistance RC \\
\hline RBNOISE(Qxx) & RENOISE(Qxx) \\
\hline RCNOISE(Qxx) & \\
\hline
\end{tabular}
1. In the above specifications, zz is to be replaced by one of the following:

DB (Magnitude, in dB); M (Magnitude); P (Phase); R (Real part); I (Imaginary part); GD (Group delay).

Table 10-26. JFET Plotting and Printing
\begin{tabular}{|c|c|}
\hline \multicolumn{2}{|l|}{DC or Transient Analysis} \\
\hline \multicolumn{2}{|l|}{Currents} \\
\hline ID(Jxx)/I(Jxx.D)/I(Jxx.1) & Drain current \\
\hline IG(Jxx)/I(Jxx.G)/I(Jxx.2) & Gate current \\
\hline IS(Jxx)/I(Jxx.S)/I(Jxx.3) & Source current \\
\hline \multicolumn{2}{|l|}{Voltages} \\
\hline VD(Jxx)/V(Jxx.D)/V(Jxx.1) & Drain voltage, in Volts \\
\hline VG(Jxx)/V(Jxx.G)/V(Jxx.2) & Gate voltage, in Volts \\
\hline VS(Jxx)/V(Jxx.S)/V(Jxx.3) & Source voltage, in Volts \\
\hline VGS(Jxx) & Gate-source voltage, in Volts \\
\hline VDS(Jxx) & Drain-source voltage, in Volts \\
\hline VT(Jxx) & Threshold voltage value, in Volts \\
\hline VDSS(Jxx) & Saturation voltage value, in Volts \\
\hline \multicolumn{2}{|l|}{Conductances} \\
\hline GDS(Jxx) & \[
\frac{\partial I_{D}}{\partial V_{D S}}
\] \\
\hline GM(Jxx) & Transconductance: \(\frac{\partial I_{D}}{\partial V_{G S}}\) \\
\hline \multicolumn{2}{|l|}{Capacitances} \\
\hline CGD(Jxx) & \(\frac{\partial Q G}{\partial V d}\) Gate/Drain capacitance \\
\hline CGS(Jxx) & \(\frac{\partial Q G}{\partial V S}\) Gate/Source capacitance \\
\hline \multicolumn{2}{|l|}{AC Analysis} \\
\hline \multicolumn{2}{|l|}{\[
\text { Currents }{ }^{1}
\]} \\
\hline Izz(Jxx.D) & Drain current. See below for meaning of zz \\
\hline Izz(Jxx.G) & Gate current. See below for meaning of zz \\
\hline Izz(Jxx.S) & Source current. See below for meaning of zz \\
\hline
\end{tabular}

Table 10-26. JFET Plotting and Printing
\begin{tabular}{|l|l|}
\hline \multicolumn{2}{|l|}{ Noise Analysis } \\
\hline RGNOISE(Jxx) & Gate access resistor noise (for JFET MODEL with RG resistance) \\
\hline
\end{tabular}
1. In the above specifications, zz is to be replaced by one of the following:
DB (Magnitude, in dB ); M (Magnitude); P (Phase); R (Real part); (Imaginary part); GD (Group delay).

Table 10-27. Diode Plotting and Printing
\begin{tabular}{|l|l|}
\hline \multicolumn{2}{|l|}{ DC or Transient Analysis } \\
\hline \multicolumn{2}{|l|}{ Currents } \\
\hline \begin{tabular}{l} 
IX(Dxx.1)/I(Dxx.POS)/ \\
ID(Dxx)/I(Dxx)
\end{tabular} & Positive output \\
\hline IX(Dxx.2)/I(Dxx.NEG) & Negative output \\
\hline Conductances \\
\hline GD(Dxx) & Diode conductance \\
\hline Capacitances & Diode capacitance \\
\hline CD(Dxx) & \\
\hline Noise Analysis & Flicker noise \\
\hline FLKNOISE(Dxx) & Thermal noise due to access resistance \\
\hline RSNOISE(Dxx) & Shot noise \\
\hline IDNOISE(Dxx) & \\
\hline
\end{tabular}

Table 10-28. Common Plotting and Printing
\begin{tabular}{|l|l|}
\hline DC or Transient Analysis & Returns the flux through the inductor Lxx. \\
\hline FLUX(Lxx) & \begin{tabular}{l} 
Current flowing into pin N of subcircuit Xxx, where N is the \\
name of the pin in the .SUBCKT statement. The node name can \\
be a node defined in a .global command.
\end{tabular} \\
\hline ISUB(Xxx.N) & \begin{tabular}{l} 
Current difference between two-pin components dipole_xx and \\
dipole_yy of any type (such as resistor, capacitor, source). If \\
dipole_yy and the comma are omitted, the current through \\
dipole_xx is printed. Current is positive when flowing from \\
pin1 to pin2.
\end{tabular} \\
\hline I(dipole_xx[, dipole_yy)
\end{tabular}

Table 10-28. Common Plotting and Printing
\begin{tabular}{|l|l|}
\hline I(device.xyz) & \begin{tabular}{l} 
Current flowing into pin xyz of any two-pin component type \\
(such as resistor, capacitor, source), where xyz may be POS, \\
NEG, PLUS or MINUS for positive pin, negative pin, plus pin, \\
or minus pin respectively. For example, .PLOT TRAN \\
I(R1.POS) requests a plot of the current going into the positive \\
pin of the resistor R1.
\end{tabular} \\
\hline I(OPAxx.xyz) \({ }^{1}\) & \begin{tabular}{l} 
Current flowing into pin xyz, where xyz may be either POS, \\
NEG, CP1 or CN1 for positive output, negative output, positive \\
control, or negative control respectively.
\end{tabular} \\
\hline IX(Xxx.N) & \begin{tabular}{l} 
Current flowing into the Nth pin of subcircuit Xxx, where N is \\
the order of the pin in the .SUBCKT statement. that is, \\
IX(XA.1)is the current flowing into the first pin of subcircuit \\
XA. If N is the name of a global node, then Eldo will return the \\
current which enters the X-instance by that global pin.
\end{tabular} \\
\hline VX(Xxx.N) & \begin{tabular}{l} 
Voltage at the Nth pin of subcircuit Xxx, where N is the order \\
of the pin in the .SUBCKT statement. Works in the same way \\
as IX(Xxx.N) above.
\end{tabular} \\
\hline I(dev1[, dev2]) & \begin{tabular}{l} 
Specifies the current between devices dev1 and dev2. If dev2 \\
and the preceding comma is omitted, ground is assumed.
\end{tabular} \\
\hline V(N1[, N2]) & \begin{tabular}{l} 
Specifies the voltage difference between nodes N1 and N2. If \\
N2 and the preceding comma is omitted, ground is assumed. In \\
the case of subcircuit nodes, N1 has the form (Xnn.N1) where \\
Xnn is the subcircuit instance.
\end{tabular} \\
\hline W(WNAME|EXPR) & \begin{tabular}{l} 
The value of a waveform WNAME which has been created \\
using the .DEFWAVE command, or the value of the waveform \\
defined by the expression EXPR. \\
.PRINT TRAN W(wave1) or .PRINT TRAN W('V(s)-V(a)')
\end{tabular} \\
\hline POW(Xinstance_name) \({ }^{2}\) & Returns the power curve dissipated in the Xinstance_name. \\
\hline POWER & \begin{tabular}{l} 
Returns the power dissipated in the entire design. This number \\
is the sum for the power dissipated in R, E, H, I, M, B, D, J \\
elements exclusively.
\end{tabular} \\
\hline VGD(N1[, N2]) & \begin{tabular}{l} 
Specifies the magnitude of the voltage difference in dB \\
between nodes N1 and N2. If only N1 is specified, ground is \\
assumed for the second node.
\end{tabular} \\
\hline \begin{tabular}{l} 
Specifies the group delay (derivative of the phase with respect \\
to the frequency) of the voltage difference between nodes N1 \\
and N2. If only N1 is specified, ground is assumed for the \\
second node. VT may be specified instead of VGD, it is \\
equivalent.
\end{tabular} \\
\hline
\end{tabular}

Table 10-28. Common Plotting and Printing
\begin{tabular}{|c|c|}
\hline VI(N1[, N2]) & Specifies the imaginary part of the voltage difference between nodes N1 and N2. If only N1 is specified, ground is assumed for the second node. \\
\hline VM(N1[, N2]) & Specifies the magnitude of the voltage difference between nodes N1 and N2. If only N1 is specified, ground is assumed for the second node. \\
\hline VP(N1[, N2]) & Specifies the phase of the voltage difference between nodes N1 and N2. If only N1 is specified, ground is assumed for the second node. \\
\hline VR(N1[, N2]) & Specifies the real part of the voltage difference between nodes N1 and N2. If only N1 is specified, ground is assumed for the second node. \\
\hline IDB(dipole_xx[, dipole_yy]) & Specifies the magnitude, in dB , of the current difference between dipole_xx and dipole_yy. If only dipole_xx is specified, the current through dipole_xx is printed. \\
\hline IGD(dipole_xx[, dipole_yy]) & Specifies the group delay (derivative of the phase with respect to the frequency) of the current difference between dipole_xx and dipole_yy. If only dipole_xx is specified, the group delay of the current through dipole_xx is printed. IT may be specified instead of IGD, it is equivalent. \\
\hline II(dipole_xx[, dipole_yy]) & Imaginary part of the current difference between dipole_xx and dipole_yy. If only dipole_xx is specified, the imaginary part of the current through dipole_xx is printed. \\
\hline IM(dipole_xx[, dipole_yy]) & Magnitude of the current difference between dipole_xx and dipole_yy. If only dipole_xx is specified, the magnitude of the current through dipole_xx is printed. \\
\hline IP(dipole_xx[, dipole_yy]) & Phase of the current difference between dipole_xx and dipole_yy. If only dipole_xx is specified, the phase of the current through dipole_xx is printed. \\
\hline IR(dipole_xx[, dipole_yy]) & Real part of the current difference between dipole_xx and dipole_yy. If only dipole_xx is specified, the real part of the current through dipole_xx is printed. \\
\hline ISUBDB(Xxx.N) & Magnitude, in dB , of the current flowing into pin N of subcircuit Xxx , where N is the name of the pin in the .SUBCKT statement. \\
\hline ISUBGD(Xxx.N) & Group delay of the current flowing into pin N of subcircuit Xxx, where N is the name of the pin in the .SUBCKT statement. \\
\hline ISUBI(Xxx.N) & Imaginary part of the current flowing into pin N of subcircuit Xxx where N is the name of the pin in the .SUBCKT statement. \\
\hline
\end{tabular}

Table 10-28. Common Plotting and Printing
\begin{tabular}{|c|c|}
\hline ISUBM(Xxx.N) & Magnitude of the current flowing into pin N of subcircuit Xxx where N is the name of the pin in the .SUBCKT statement. \\
\hline ISUBP(Xxx.N) & Phase of the current flowing into pin N of subcircuit Xxx where N is the name of the pin in the .SUBCKT statement. \\
\hline ISUBR(Xxx.N) & Real part of the current flowing into pin N of subcircuit Xxx where N is the name of the pin in the .SUBCKT statement. \\
\hline \(\operatorname{IXDB}\) (Xxx.N) & Magnitude in dB, of the current flowing into the Nth pin of subcircuit Xxx , where N is the order of the pin in the .SUBCKT statement. If N is the name of a global node, then Eldo will return the magnitude in dB of the current which enters the X instance by that global pin. \\
\hline IXGD(Xxx.N) & Group delay of the current flowing into the Nth pin of subcircuit Xxx, where N is the order of the pin in the .SUBCKT statement. If N is the name of a global node, then Eldo will return the group delay of the current which enters the Xinstance by that global pin. \\
\hline IXI(Xxx.N) & Imaginary part of the current flowing into the Nth pin of subcircuit Xxx. If N is the name of a global node, then Eldo will return the imaginary part of the current which enters the Xinstance by that global pin. \\
\hline IXM(Xxx.N) & Magnitude of the current flowing into the Nth pin of subcircuit Xxx. If N is the name of a global node, then Eldo will return the magnitude of the current which enters the X -instance by that global pin. \\
\hline IXP(Xxx.N) & Phase of the current flowing into the Nth pin of subcircuit Xxx. If N is the name of a global node, then Eldo will return the phase of the current which enters the X-instance by that global pin. \\
\hline IXR(Xxx.N) & Real part of the current flowing into the Nth pin of subcircuit Xxx . If N is the name of a global node, then Eldo will return the real part of the current which enters the X-instance by that global pin. \\
\hline \(\operatorname{SDB}(\mathrm{i}, \mathrm{j})\) & Magnitude in dB, of S parameter Sij. \\
\hline SR(i, j) & Real part of the S parameter Sij. \\
\hline SI(i, j) & Imaginary part of the S parameter Sij . \\
\hline WDB(WNAME) & Magnitude in dB, of the waveform WNAME created using a .DEFWAVE command. \\
\hline WI(WNAME) & Imaginary part of the waveform WNAME created using a .DEFWAVE command. \\
\hline
\end{tabular}

Table 10-28. Common Plotting and Printing
\begin{tabular}{|l|l|}
\hline WM(WNAME) & \begin{tabular}{l} 
Magnitude of the waveform WNAME created using a \\
.EFFWAVE command.
\end{tabular} \\
\hline WP(WNAME) & \begin{tabular}{l} 
Phase of the waveform WNAME created using a .DEFWAVE \\
command.
\end{tabular} \\
\hline WR(WNAME) & \begin{tabular}{l} 
Real part of the waveform WNAME created using a \\
.DEFWAVE command.
\end{tabular} \\
\hline Noise Analysis & Linear input noise when performing a Noise analysis. \\
\hline INOISE \({ }^{3}\) & Linear output noise when performing a Noise analysis. \\
\hline ONOISE & Input noise in dB when performing a Noise analysis. \\
\hline DB(INOISE) & Output noise in dB when performing a Noise analysis. \\
\hline DB(ONOISE) & \begin{tabular}{l} 
Noise contribution of component compx to the total output \\
noise of the circuit.
\end{tabular} \\
\hline NOISE(compx) & \begin{tabular}{l} 
Noise circle for a given value of a Noise Figure (SNF_val). \\
When this value is not specified, the circle is plotted for a Noise \\
Figure value corresponding to the actual circuit
\end{tabular} \\
\hline NOISE NC \({ }^{4}\) &
\end{tabular}
1. In the MOS and bipolar current print commands, the current is positive when it enters the device.
2. In all cases, the power stored in capacitances is ignored, only dissipated power is taken into account. Power is measured only in DC and TRANSIENT analyses.
3. For more information on the use of INOISE and ONOISE, see the example in ".NOISE" on page 744.
4. For more information on NOISE NC see "Two-port Noise Circles" on page 820.

\section*{Element Output}

LVnn (Ex) or LXnn(Ex), where:
LV This formulation is used to obtain user-input parameters.
LX This formulation is used to obtain computed values such as charges, capacitances, and derivatives.
\(\mathrm{nn} \quad\) Index to select the appropriate output.
Ex Name of the element.
Note \(\qquad\)
In the table below, the LX values which correspond to voltage (such as Lxo for diodes) are computed using the intrinsic nodes, not the extrinsic nodes (the behavior in Eldo releases pre-v5.9).
The names in parentheses are aliases.

Table 10-29. Element Output
\begin{tabular}{|c|c|}
\hline \multicolumn{2}{|l|}{Resistors} \\
\hline LV1 & Conductance at analysis temperature \\
\hline LV2 & Resistance at reference temperature \\
\hline LV3 & First temperature coefficient TC1 \\
\hline LV4 & Second temperature coefficient TC2 \\
\hline \multicolumn{2}{|l|}{Capacitors} \\
\hline LV1 & Computed capacitance \\
\hline LX0 (Q) & Charge stored in capacitor \\
\hline LX1 (I) & Current flowing through capacitor \\
\hline LX2 (VDIP) & Voltage across capacitor \\
\hline LX3 & Capacitance value \\
\hline \multicolumn{2}{|l|}{Inductors} \\
\hline LV1 & Computed inductance \\
\hline LX0 & Flux in the inductor \\
\hline LX1 (VDIP) & Voltage across inductor \\
\hline LX2 (I) & Current flowing through inductor \\
\hline LX4 & Inductance value \\
\hline \multicolumn{2}{|l|}{Voltage-Controlled Voltage Sources} \\
\hline LX0 (VDIP) & Source voltage \\
\hline LX1 (I) & Current through source \\
\hline \multicolumn{2}{|l|}{Current-Controlled Current Sources} \\
\hline LX0 (I) & Current through source \\
\hline \multicolumn{2}{|l|}{Current-Controlled Voltage Sources} \\
\hline LX0 (VDIP) & Source voltage \\
\hline LX1 (I) & Source current \\
\hline \multicolumn{2}{|l|}{Diodes} \\
\hline LV1 & Diode area factor \\
\hline LX0 (VDIP) & DC/transient voltage across diode \\
\hline LX1 (I) & Current through diode; gmin effect is not taken into account \\
\hline
\end{tabular}

Table 10-29. Element Output
\begin{tabular}{|c|c|}
\hline LX2 (GD) & Equivalent conductance \\
\hline LX3 (Q) & Charge of diode capacitor \\
\hline LX4 & Dynamic current through diode \\
\hline LX5 (CD) & Total diode capacitance \\
\hline \multicolumn{2}{|l|}{BJTs} \\
\hline LV1 & Area factor \\
\hline LV5 & FT \\
\hline LV8 & LOG10(IC) \\
\hline LV9 & LOG10(IB) \\
\hline LV10 & BETA \\
\hline LV11 & LOG10(BETA) Current \\
\hline LX0 & VBE \\
\hline LX1 & Base-collector voltage \\
\hline LX2 & Collector current \\
\hline LX3 & Base current \\
\hline LX4 & \(\mathrm{Gpi}=\mathrm{Ib} / \mathrm{Vbe}\), constant vbc \\
\hline LX5 & \(\mathrm{Gmu}=\mathrm{Ib} / \mathrm{Vbc}\), constant vbe \\
\hline LX6 & \(\mathrm{Gm}=\mathrm{Ic} / \mathrm{Vbe}\), constant vbc \\
\hline LX7 & GO = Ic/Vce, constant vbe \\
\hline LX19 (CPI) & cbe capacitance \\
\hline LX20 (CMU) & cbc capacitance \\
\hline \multicolumn{2}{|l|}{JFETs} \\
\hline LV1 & JFET area factor \\
\hline LX0 & VGS \\
\hline LX1 (VGD) & Gate-drain voltage \\
\hline LX2 (CGS) & Gate-to-source \\
\hline LX3 (IDS) & Drain current \\
\hline LX4 (IGD) & Gate-to-drain current \\
\hline LX5 (GM) & Transconductance \\
\hline LX6 (GDS) & Drain-source transconductance \\
\hline LX9 (QG) & Gate-source charge \\
\hline
\end{tabular}

Table 10-29. Element Output
\begin{tabular}{|c|c|}
\hline LX11 (GD) & Gate-drain capacitance \\
\hline LX18 (GMB) & Drain-body trans-conductance \\
\hline \multicolumn{2}{|l|}{MOSFETs} \\
\hline LV1 & Effective channel Length \\
\hline LV2 & Effective channel width \\
\hline LV3 & Effective area of the drain diode \\
\hline LV4 & Effective area of the source diode \\
\hline LV9 (VT) & Threshold "on" voltage \\
\hline LV10 (VDSS) & Saturation voltage \\
\hline LV11 & Effective drain diode periphery \\
\hline LV12 & Effective source diode periphery \\
\hline LV13 & Drain resistance (squares) \\
\hline LV14 & Source resistance (squares) \\
\hline LV15 & Charge sharing coefficient \\
\hline LV16 & Effective drain conductance (1/RDeff) \\
\hline LV17 & Effective source conductance (1/RSeff) \\
\hline LX0 (VBD) & Bulk-drain voltage \\
\hline LX1 (VBS) & Bulk-source voltage \\
\hline LX2 (VGS) & Gate-source voltage \\
\hline LX3 (VDS) & Drain-source voltage \\
\hline LX4 (IDS) & DC drain current \\
\hline LX5 (IBS) & DC source-bulk diode current \\
\hline LX6 (IBD) & DC drain-bulk diode current \\
\hline LX7 (GM) & DC gate transconductance \\
\hline LX8 (GDS) & DC drain-source conductance \\
\hline LX9 (GMBS) & DC substrate transconductance \\
\hline LX10 (GMIBD) & Conductance of the drain diode \\
\hline LX11 (GMIBS) & Conductance of the source diode \\
\hline LX12 (QB) & Bulk charge \\
\hline LX14 (QG) & Gate charge \\
\hline LX16 (QD) & Channel charge \\
\hline
\end{tabular}

Table 10-29. Element Output
\begin{tabular}{|l|l|}
\hline LX18 (CGG) & \(\mathrm{dQg} / \mathrm{dVgb}\) \\
\hline LX19 (CGD) & \(\mathrm{dQg} / \mathrm{dVdb}\) \\
\hline LX20 (CGS) & \(\mathrm{dQg} / \mathrm{dVsb}\) \\
\hline LX21 (CBG) & dQb/dVgb \\
\hline LX22 (CBD) & dQb/dVdb \\
\hline LX23 (CBS) & dQb/dVsb \\
\hline LX24 (QBD) & Drain-bulk charge \\
\hline LX26 (QBS) & Source-bulk charge \\
\hline LX28 & Bulk-source capacitance \\
\hline LX29 & Bulk-drain capacitance \\
\hline LX32 (CDG) & dQd/dVgb \\
\hline LX33 (CDD) & dQd/dVdb \\
\hline LX34 (CDS) & dQd/dVsb \\
\hline
\end{tabular}

\section*{Printing Internal Pin Values}

To measure the intrinsic value of a pin you use the same syntax as for measuring its extrinsic value. However, you use an index number greater than the number of pins available that corresponds to the pins position. For example, the source voltage pin is the third pin of a MOSFET and there are 4 pins in total. Therefore, to obtain the intrinsic source voltage of this MOSFET you would use:
```

.PLOT V(Mx.7)

```

To obtain the intrinsic value of the drain current pin of a JFET you would use:
.PLOT I(JX.4)
Note \(\qquad\)
If the position number used is greater than the index available for the device it will return a value of zero.

\section*{Monitoring of Hierarchical Nodes}

More information related to the internal status of devices can be displayed. The following is a list of variables displayed together with the syntax to address them. This output format is used to specify nodes that lie within subcircuits. The node itself cannot be referenced directly from the 'top-level' of the circuit and so it must be addressed through the levels of the subcircuit by separating elements with periods (.) in the output control statement. The example below illustrates this output format.
```

.subckt sc1 n10 n12
r10 n10 n11 0.2
x2 n11 n12 sc2
.ends sc1
.subckt sc2 n20 n22
r20 n20 n21 0.1k
r22 n21 n22 0.1k
.ends sc2
x1 a b sc1
.print tran v(x1.x2.n21) v(a) v(b)

```

The above example specifies the output of three nodes. The node \(\mathrm{x} 1 . \mathrm{x} 2 . \mathrm{n} 21\) is created as the second pin of resistor \(\mathbf{r} 20\), which is an element of the subcircuit \(s c 2\), instantiated using instance \(\mathbf{x} 2\). The instance \(\mathbf{x} 2\) is itself nested in the subcircuit sc1, instantiated using instance \(\mathbf{x} 1\).

\section*{Transmission Lines}
- I(Txx.N1) I(Txx.N2) I(Txx.N3) I(Txx.N4)

Prints the current out of transmission lines.

\section*{Two-port Parameters}

Table 10-30. Two-port Parameters
\begin{tabular}{|c|c|}
\hline \multicolumn{2}{|l|}{Two-port Stability Factors (for more information, see Two-Port Stability Factors of the Eldo RF User's Manual)} \\
\hline KFACTOR & \begin{tabular}{l}
Computes the stability factor for 2-ports.
\[
\frac{\left(1.0-|S 11|^{2}-|S 22|^{2}-|S 11 \times S 22-S 12 \times S 21|^{2}\right)}{(2 \times|S 12 \times S 21|)}
\] \\
S11, S22, and so on, are the \(S\) parameters.
\end{tabular} \\
\hline BFACTOR & Rollet stability factor.
\[
B F A C T O R=\frac{1-\left|S_{22}\right|^{2}}{\left|S_{11}-\Delta S_{22}^{*}\right|+\left|S_{22} \cdot S_{11}\right|}
\] \\
\hline MUFACTOR & Rollet stability factor.
\[
\text { MUFACTOR }=\frac{1+\left|S_{11}\right|^{2}-\left|S_{22}\right|^{2}+|\Delta|^{2}}{\left|S_{11}-\Delta S_{22} *\right|} \text { where } \Delta=S_{11} \cdot S_{22}-\left(S_{12} \cdot S_{21}\right)
\] \\
\hline MUFACTOR_L & \begin{tabular}{l}
Rollet stability factor (Load). \\
MUFACTOR_L \(=\frac{1-\left|S_{11}\right|^{2}}{\left|S_{22}-\left(S_{11}\right)^{*} \cdot \Delta\right|+\left|S_{12} \cdot S_{21}\right|}\) where \(\Delta\) is as above.
\end{tabular} \\
\hline
\end{tabular}

Table 10-30. Two-port Parameters
\begin{tabular}{|l|l|}
\hline MUFACTOR_S & \begin{tabular}{l} 
Rollet stability factor (Source). \\
MUFACTOR_S \(=\frac{1-\left|S_{22}\right|^{2}}{\left|S_{11}-\left(S_{22}\right)^{*} \cdot \Delta\right|+\left|S_{21} \cdot S_{12}\right|}\) where \(\Delta\) is as above.
\end{tabular} \\
\hline \begin{tabular}{l} 
Two-port Noise Parameters \\
(for more information, see Two-Port Noise Parameters of the Eldo RF User's Manual)
\end{tabular} \\
\hline NFMIN_mag & \begin{tabular}{l} 
Minimal noise figure (magnitude) of the two-port. \\
\(N F M I N ~=1+2 \cdot \frac{R e\left\{C_{12}^{A}\right\}+G O P T \cdot C_{11}^{A}}{4 \cdot k \cdot T}\)
\end{tabular} \\
\hline NFMIN_dB & \begin{tabular}{l} 
Minimal noise figure of the two-port (in decibels).
\end{tabular} \\
\hline GOPT & \begin{tabular}{l} 
Real part of the optimal source admittance.
\end{tabular} \\
\hline BOPT \(=\frac{1}{C_{11}^{A}} \sqrt{C_{11}^{A} \cdot C_{22}^{A}-\left(\text { Im }\left\{C_{12}^{A}\right\}\right)^{2}}\)
\end{tabular}

\section*{Table 10-30. Two-port Parameters}

\section*{Two-port Noise Circles}
(for more information, see Two-Port Noise Circles of the Eldo RF User's Manual)
\begin{tabular}{|c|c|}
\hline NC & A noise circle is plotted for a given value of a Noise Figure (SNF_val). When this value is not specified, the circle is plotted for a Noise Figure value corresponding to the actual circuit.
\[
\begin{aligned}
& \text { center }=\frac{\Gamma_{o p t}}{1+N_{i}} \\
& \text { radius }=\sqrt{\frac{N_{i}^{2}+N_{i} \cdot\left(1-\left|\Gamma_{o p t}\right|^{2}\right)}{1+N_{i}}} \\
& N_{i}=\frac{(\text { SNF_val }-N F M I N) \cdot\left|1+\Gamma_{o p t}\right|^{2}}{4 \cdot \mathrm{RNEQ}}
\end{aligned}
\] \\
\hline
\end{tabular}

\section*{Two-port Constant Gain Circles}
(for more information, see Two-Port Constant Gain Circles of the Eldo RF User's Manual)
GAC
Available Gain Circle. Determines constant gain contour at the input port. With respect to the definition of GA and GP, GAC represents an optimum match at the output port.
\[
\text { center }=\frac{G A\left(S_{11}^{*}-S_{22} \Delta^{*}\right)}{\left|S_{21}\right|^{2}+G A\left(\left|S_{11}\right|^{2}-|\Delta|^{2}\right)}
\]
where \(\Delta=\left(S_{11} S_{22}-S_{21} S_{12}\right)\)
radius \(=\frac{\sqrt{1-2 \text { KFACTOR }\left|S_{21} S_{12}\right| \frac{G A}{\left|S_{21}\right|^{2}}+\left(\left|S_{21} S_{12}\right| \frac{G A}{\left|S_{21}\right|^{2}}\right)^{2}}}{\left|1+\frac{G A}{\left|S_{21}\right|^{2}}\left(\left|S_{11}\right|^{2}-|\Delta|^{2}\right)\right|}\)

Table 10-30. Two-port Parameters
\begin{tabular}{|c|c|}
\hline GPC & Power Gain Circle. Determines constant gain contour at the output port. With respect to the definition of GA and GP, GPC represents an optimum match at the input port.
\[
\text { center }=\frac{G P\left(S_{22}^{*}-S_{11} \Delta^{*}\right)}{\left|S_{21}\right|^{2}+G P\left(\left|S_{22}\right|^{2}-|\Delta|^{2}\right)}
\]
\[
\text { radius }=\frac{\sqrt{1-2 K F A C T O R\left|S_{21} S_{12}\right| \frac{G P}{\left|S_{21}\right|^{2}}+\left(\left|S_{21} S_{12}\right| \frac{G P}{\left|S_{21}\right|^{2}}\right)^{2}}}{\left|1+\frac{G P}{\left|S_{21}\right|^{2}}\left(\left|S_{22}\right|^{2}-|\Delta|^{2}\right)\right|}
\] \\
\hline \multicolumn{2}{|l|}{Two-port Gain Parameters (for more information, see Two-Port Gain Parameters of the Eldo RF User's Manual)} \\
\hline GA_mag & Available power Gain (magnitude). This is the ratio of the power available from the two-port circuit to the power available from the source when the load is conjugately matched to the output port of the circuit \(\left(\Gamma_{\mathrm{L}}=\operatorname{conj}\left(\Gamma_{\text {OUT }}\right)\right)\).
\[
G A=\frac{1-\left|\Gamma_{s}\right|^{2}}{\left|1-S_{11} \Gamma_{s}\right|^{2}}\left|S_{21}\right|^{2} \frac{1}{1-\left|\Gamma_{O U T}\right|^{2}}
\] \\
\hline GA_dB & Available power Gain (in decibels). \\
\hline GAM_mag & \begin{tabular}{l}
Maximum Available power Gain (magnitude). When the input port of the circuit is conjugately matched to the source impedance and the output port of the circuit is conjugately matched to the load impedance \(\left(\Gamma_{\mathrm{S}}=\operatorname{conj}\left(\Gamma_{\mathrm{IN}}\right)\right.\) and \(\Gamma_{\mathrm{L}}=\) \(\operatorname{conj}\left(\Gamma_{\text {OUT }}\right)\) ). \\
For a bilateral case:
\[
G A M=\left|\frac{S_{21}}{S_{12}}\right|\left(\text { KFACTOR }-\sqrt{K F A C T O R^{2}-1}\right) \quad G A M=\left|\frac{S_{21}}{S_{12}}\right|
\]
\[
\text { if } K F A C T O R>1 \quad \text { if } K F A C T O R \leq 1
\] \\
For the kfactor, see "KFACTOR" on page 818. \\
For a unilateral case, see "GAUM_mag" on page 822.
\end{tabular} \\
\hline GAM_dB & Maximum Available power Gain (in decibels). \\
\hline GASM_mag & Maximum Available Stable Gain (magnitude). See the GAM definition above.
\[
G A S M=\left|\frac{S_{21}}{S_{12}}\right|
\] \\
\hline GASM_dB & Maximum Available Stable Gain (in decibels). \\
\hline
\end{tabular}

Table 10-30. Two-port Parameters
\begin{tabular}{|c|c|}
\hline GP_mag & \begin{tabular}{l}
Power Gain (magnitude). This is the ratio of the power delivered to the load to the power input to the two-port circuit when the input port of the circuit is conjugately matched to the source impedance \(\left(\Gamma_{\mathrm{S}}=\operatorname{conj}\left(\Gamma_{\mathrm{IN}}\right)\right)\).
\[
G P=\frac{1-\left|\Gamma_{L}\right|^{2}}{\left|1-S_{22} \Gamma_{L}\right|^{2}}\left|S_{21}\right| \frac{1}{1-\left|\Gamma_{I N}\right|^{2}} \quad \begin{gathered}
\Gamma_{L}=\frac{Z_{L}-Z_{0}}{Z_{L}+Z_{0}} \\
\Gamma_{I N}=S_{11}+\frac{S_{12} S_{21} \Gamma_{L}}{1-S_{22} \Gamma_{L}}
\end{gathered}
\] \\
\(Z_{\mathrm{S}} \quad\) Source impedance \\
\(\mathrm{Z}_{\mathrm{L}} \quad\) Load impedance \\
\(\Gamma_{\mathrm{S}}\) Source reflection coefficient \\
\(\Gamma_{\mathrm{L}}\) Load reflection coefficient \\
\(\mathrm{Z}_{0} \quad\) Characteristic impedance (by default \(50 \Omega\); to modify this value see " \(\mathrm{ZCHAR}=\mathrm{VAL}\) " on page 1022).
\end{tabular} \\
\hline GP_dB & Power Gain (in decibels). \\
\hline GAUM_mag & Maximum Unilateral transducer power Gain (magnitude). This is the transducer gain when the circuit ports are both optimally matched \(\left(\Gamma_{\mathrm{S}}=\operatorname{conj}\left(\Gamma_{\mathrm{IN}}\right)\right.\) and \(\Gamma_{\mathrm{L}}=\operatorname{conj}\left(\Gamma_{\text {OUT }}\right)\) and \(\left.\mathrm{S}_{12}=0\right)\).
\[
G A U M=\frac{1}{1-\left|S_{11}\right|^{2}}\left|S_{21}\right|^{2} \frac{1}{1-\left|S_{22}\right|^{2}}
\] \\
\hline GAUM_dB & Maximum Unilateral transducer power Gain (in decibels). \\
\hline TGP_mag & Transducer Power Gain (magnitude). This is the ratio of the power delivered to the load to the power available from the source.
\[
T G P=\frac{1-\left|\Gamma_{s}\right|^{2}}{\left|1-S_{11} \Gamma_{s}\right|^{2}}\left|S_{21}\right| \frac{1-\left|\Gamma_{L}\right|^{2}}{\left|1-\Gamma_{O U T} \Gamma_{L}\right|^{2}}
\] \\
\hline TGP_dB & Transducer Power Gain (in decibels). \\
\hline \multicolumn{2}{|l|}{\begin{tabular}{l}
Two-port Stability Circles \\
(for more information, see Two-Port Stability Circles of the Eldo RF User's Manual)
\end{tabular}} \\
\hline SSC & Source Stability Circle. It determines the locus of \(\Gamma_{\mathrm{S}}\) which produce \(\left|\Gamma_{\text {OUT }}\right|=1\).
\[
\begin{aligned}
& \text { center }=\frac{S_{22} \Delta^{*}-S_{11}^{*}}{|\Delta|^{2}-\left|S_{11}\right|^{2}} \\
& \text { radius }=\left|\frac{S_{12} S_{21}}{|\Delta|^{2}-\left|S_{11}\right|^{2}}\right|
\end{aligned}
\] \\
\hline
\end{tabular}

Table 10-30. Two-port Parameters
\begin{tabular}{|l|l|}
\hline LSC & \begin{tabular}{l} 
Load Stability Circle. It determines the locus of \(\Gamma_{\mathrm{L}}\) which produce \(\left|\Gamma_{\text {IN }}\right|=1\). \\
center \(=\frac{S_{11} \Delta^{*}-S_{22}^{*}}{|\Delta|^{2}-\left|S_{11}\right|^{2}}\) \\
\\
\\
radius \(=\left|\frac{S_{12} S_{21}}{|\Delta|^{2}-\left|S_{22}\right|^{2}}\right|\) \\
\hline
\end{tabular} \\
\hline
\end{tabular}

\section*{Plotting an analog signal as a digital bus}

To enable the plotting of an analog signal as a digital bus, a setup command is required (.DEFPLOTDIG) to be used in conjunction with the vDIg parameter of the .PLOT command.
```

.DEFPLOTDIG VTH1=2.2 VTH2=2.7
.PLOT TRAN VDIG(n2)

```

When .defplotdig is used in conjunction with . plot vdig, the signal node \(n 2\) is plotted as a digital curve and will only have values of " 1 " or " 0 ".
- .DEFPLOTDIG [VTh[1]=VAL [VTH2=VAL]]

This is used as a precursor to VDIG in order to plot an analog curve as digital with reference to any stated threshold voltage(s).
- \(\mathrm{VTH}[1]=\mathrm{VAL}\)

If a voltage threshold is specified, the bus of an analog signal is plotted as a bus (hexadecimal format), else all the different signals of the bus are plotted separately in the waveform viewer as analog waves. (vтн and vтн1 are equivalent to ensure backwards compatibility.)
- VTH2=VAL

This can be used to plot the indeterminate value as shown below:
When only vTH1 is given:
If value \(<\mathrm{VTH}\) then logic state 0 .
If value \(>\mathrm{V}\) тн then logic state 1 .
When both vтн1 and vтн 2 are given:
If value < vтн1 then logic state 0 .
If VTH1 < value < VTH2 then state X.
If value \(>\mathrm{v}\) тн2 then logic state 1 .

\section*{Examples}
```

.PLOT TRAN V(a) V(b)

```

Specifies that the voltages for \(\mathbf{V}(\mathrm{a})\) and \(\mathbf{v}(\mathrm{b})\) be plotted. EZwave will plot both \(\mathbf{v}(\mathrm{a})\) and \(\mathbf{v}(\mathrm{b})\) on the Y -axis with the time plotted on the X -axis.
. PLOT TRAN \(V(a)\) (VERSUS) \(\mathbf{V}(b)\)

Specifies that EZwave will plot \(\mathbf{v}(\mathrm{a})\) on the Y-axis against \(\mathbf{v}(\mathrm{b})\), which will be plotted on the X -axis.
```

.plot tran v(1) v(2) v(3, 4) i(v1, v2)

```

Specifies that the voltage at the nodes 1 and 2, the voltage difference between the nodes 3 and 4 , and the current difference of the voltage sources v 1 and v 2 be plotted.
```

.plot ac vdb(4) (-50, 50) idb(v6) (-75, 75)

```

This is the same example as the last except that the dB plot limits have changed. The new limits are -50 dB to +50 dB for the voltage at node 4 , and -75 dB to +75 dB for the current through voltage source v 6 .
```

.plot ac vm(4) unit=Watts

```

Specifies that the voltage at node 4 be plotted, and that the Y -axis units of the plot be Watts.
```

.PLOT NOISE NOISE(r1)

```

Eldo will plot the noise generated by the resistor r1 in the circuit.
```

.plot noise noise(X1)

```

Returns the total noise contribution of a subcircuit instance (x1). Its value is the sum of the noise of all elements that are part of the specified subcircuit instance.
```

.FOUR LABEL = t1 V(a)
.PLOT FOUR FOURDB(t1)

```

Eldo will plot the value (in dB ) at 5 Meg for the FFT done on \(\mathrm{V}(\mathrm{a})\).
```

.PLOT VX(M1.7)
.PLOT VX(Q1.3)
.PLOT VX(R1.2)

```

Eldo will plot values according to the following: vx (M1.7) refers to the intrinsic source voltage, \(\mathrm{VX}(Q 1.3)\) refers to the extrinsic emitter voltage, \(\mathrm{VX}(\mathrm{R1.2})\) refers to the 'second' pin of resistor R1.
.PLOT TRAN \(\mathrm{w} 1=\mathrm{v}(\mathrm{X} 1 . \mathrm{X} 2 . \mathrm{X} 3 . \mathrm{X} 4 . \mathrm{OUT})\)
Here, the wave \(\mathrm{v}(\mathrm{X} 1 . \mathrm{x} 2 . \mathrm{x} 3 . \mathrm{x} 4\). OUT) will be plotted inside EZwave, but the legend will be w1 and not v (x1.x2.x3.x4.out).
. PLOT AC \(\mathrm{S}(1,1) \mathrm{S}(2,2)\) (SMITH)
Shows syntax for specifying EZwave to display the waves in a Smith chart. In the example above, both \(S(1,1)\) and \(S(2,2)\) will be on the same Smith chart.
.PLOT AC S12 (POLAR)
Shows syntax for specifying EZwave to display the waves in a Polar chart.
.PLOT NOISE NFMIN_MAG

Plots the minimal noise figure for two port noise.
```

.PLOT NOISE YVAL (RNEQ, 10k)

```

In the example above, the \(y\)-axis value of waveform WAVE is returned when the equivalent noise resistance reaches 10 k .
```

.PLOT OPT WOPT(FOO)

```

Plots the extracted wave FOO which was generated during optimization.
```

.DSP LABEL=LBL2 MODEL=PSD_PERIODO V(1)
.PLOT DSP DSPDB(LBL2)

```

Displays DSP results. Eldo will plot the values (in dB ) for the DSP done on \(\mathrm{v}(1)\).
```

.DATA dataname component1 component2

+ x1 c1y1 c2y1
+ x2 c1y2 c2y1
..
+ xn c1yn c2yn
.ENDDATA

```
. PLOT TRAN DATA (dataname, component2)

Eldo will plot a wave defined with the .DATA statement.
.PLOT FOUR fourdb(foo) (CONTINUOUS)
Plots the FFT waveforms in continuous drawing mode instead of the default spectral mode.
The following full netlist example shows how to plot the S11, Zin and Yin of a node (IN) on a Smith chart using STOSMITH, ZTOSMITH, and YTOSMITH functions.
```

VIN IN 0 RPORT=50 IPORT=1 FOUR FUND1 MA (1) 1 0
RIN IN 1 RIN
CIN IN O CIN
LIN 1 0 LIN
.PARAM F1=1G Z0=50 RIN=Z0
.PARAM CIN=1p LIN=1f
.SST FUND1=F1 NHARM1=1
.STEP PARAM F1 DEC 10 1k 10G
.DEFWAVE ZIN=(1+S (1,1))/(1-S (1,1))*50
.DEFWAVE YIN=1/W(ZIN)
.EXTRACT FSST LABEL=S_EXT STOSMITH(YVAL(S (1,1),F1))
.PLOT MEAS (S_EXT) (SMITH,50)
.EXTRACT FSST LABEL=Z_EXT ZTOSMITH(YVAL(W(ZIN),F1),50)
.PLOT MEAS(Z_EXT) (SMITH,50)
.EXTRACT FSST LABEL=Y_EXT YTOSMITH(YVAL (W(YIN),F1),50)
.PLOT MEAS(Y_EXT) (SMITH,50)
.END

```

As can be seen in EZwave, the three functions produce the same waveform.

Figure 10-5. Smith chart plot using STOSMITH/ZTOSMITH/YTOSMITH functions


\section*{.PLOTBUS}

\section*{Plotting of Bus Signals}
```

.PLOTBUS BNAME [VTH[1]=VAL [VTH2=VAL]]

+ [BASE=OCT |DEC|BIN|HEX] [RADIX=UNSIGNED| 2COMP ] [(ANALOG)]
.PLOTBUS BNAME[MSB:LSB]|BNAME[MSB:LSB](MSB:LSB)|BNAMEMSB:LSB
+ [BASE=OCT |DEC|BIN|HEX] [RADIX=UNSIGNED| 2COMP] [(ANALOG)]

```

This command plots all the bits of a bus, previously defined via the .setbus and using .sigbus to send a value. .setbus can be implicitly declared, providing that BNAME [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used.

\section*{Parameters}
- BNAME

Bus name, previously defined via the . SETBUS command, unless BNAME [MSB: LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used, in which case .SETBUS is implicitly declared.
- VTH[1]=VAL

If a voltage threshold is specified, the bus of an analog signal is plotted as a bus (hexadecimal format), else all the different signals of the bus are plotted separately in the waveform viewer as analog waves. (vтн and vтн1 are equivalent to ensure backward compatibility.)
- VTH2=VAL

This can be used to plot the indeterminate value as shown below:
When only vtit is given:
If value \(<\mathrm{V}\) th then logic state 0 .
If value \(>\mathrm{VTh}\) then logic state 1 .
When both vini and viriz are given:
If value < vini then logic state 0 .
If vTH1 < value < vTH2 then state X.
If value \(>\) vтн2 then logic state 1.
- MSB:LSB

Series of bit names, the most significant bit being defined first. This mechanism can be used to implicitly declare . setbus.
- base

Keyword indicating that the bus signal number system is to be defined.
ост
Keyword indicating that bus signals are defined in octal.
DEC
Keyword indicating that bus signals are defined in decimal. Default.

BIN
Keyword indicating that bus signals are defined in binary.
HEX
Keyword indicating that bus signals are defined in hexadecimal.
- RADIX=UNSIGNED | 2COMP

Defines how negative values inside bus patterns are managed.
UNSIGNED—negative values are forbidden (default)
2COMP-the two's complement of the value is done
- analog

Allows to plot the bus as an analog waveform using the bus decimal values. Unit is Volts.

\section*{Examples}

In order to display the output of a bus, you can use the following syntax:
```

.PLOTBUS Y<instance_name> -> <vector_name>

```

The following example shows how a second voltage threshold can be used:
```

.plotbus foo vth=1 vth2=4
.checkbus OUT_BUS_2 vth=1 vth2=4 base=bin

+ 1000ps 01
+ 7000ps x
+ 12000ps 11
+ 15000ps 01
+ 19500ps 01
+ 20000ps 10
+ 22000ps 10
+ 30000ps 01

```

Refer to ".CHECKBUS" on page 561 for more information.
.plotbus can be used to implicitly declare .setbus, providing that BNAME [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used as shown below:
```

.PLOTBUS SELECT[2:0]
.PLOTBUS DOUT<3:0> VTH=1.65

```
is equivalent to:
```

.SETBUS SELECT SELECT[2] SELECT[1] SELECT[0]
.PLOTBUS SELECT
.SETBUS DOUT DOUT<3> DOUT<2> DOUT<1> DOUT<0>
.PLOTBUS DOUT VTH=1.65

```

The following example shows the most significant bit as 1 and the least significant as 5 , where the bus name is foo.
```

.PLOTBUS fool:5 vth=3

```

\section*{.PRINT}

\section*{Printing of Results}
.PRINT [ANALYSIS] [alias_name=]OVN
The .PRINT command defines the contents of a tabular listing of any number of output variables. The sampling period of the .PRINT command is equivalent to the TPRINT parameter of the .TRAN command.

By default, the quantities listed in a .PRINT command are not written to the ASCII .chi output file. This avoids creating huge .chi output files in the case of large simulations. The ASCII outputs are still supported for SPICE compatibility reasons, although seldom used. To force Eldo to generate these output quantities in the ASCII output file, specify the -ascii command-line flag when invoking Eldo or include the option ASCII in the netlist (see "ASCII" on page 998). Symbols such as *, +, and so on, will be used to identify each quantity, to create ASCII waveforms in the .chi output file.

\section*{Parameters}
- ANALYSIS

Optional. Specifies the analysis type, which can be useful in the case of multiple types of analysis in the .cir file. Can be one of the following:

DC
Specifies that the plots are required for a DC analysis. Note, not available for a single analysis.

AC
Specifies that the plots are required for an AC analysis.

\section*{TRAN}

Specifies that the plots are required for a transient analysis.

\section*{NOISE}

Specifies that the plots are required for a noise analysis.
SSTAC|SSTXF|SSTNOISE|SSTJITTER|TMODSST|FMODSST|FOURMODSST|TSST|
FSST|SSTSTABIL
Please refer to the Display Command Syntax chapter of the Eldo RF User's Manual for more information regarding these RF options.

FOUR
Displays FFT results. See "FOURxx (label_name)" on page 799 for display options.

DSP
Displays DSP results. See "DSPxx (label_name)" on page 799 for display options.
- alias_name

Refers to the wave name in the ASCII and binary output files. The alias_name will be the legend displayed inside the wave viewer for the plotted wave as specified by the plot specifications in ovN.
- OVN

Output variable name. A list of plot specifications can follow. Mandatory. These are listed in "Plot Specifications (OVN)" on page 799 of the .PLOT command.

\section*{Related options}
nOASCII (see "NOASCII" on page 1004)

\section*{Examples}
```

.print ac vdb(n2, n4) vp(n2, n4)

```

Requests that the output of the magnitude between node \(n 2\) and node \(n 4 \mathrm{in} \mathrm{dB}\) and the phase between \(n 2\) and \(n 4\) in degrees be printed.
```

.print noise inoise onoise noise(m1) noise(m2)

```

Requests that the input and output noise from a Noise analysis be printed, together with the noise contributions of components \(\mathbf{m} 1\) and \(\mathbf{m} 2\) to the total output noise.
```

.defwave z=(V(a)-V(b))/i(rl)
.print ac wr(z) wi(z)

```

Requests print out of the real and imaginary parts of the new waveform, \(z\), created by the .DEFWAVE command.

\section*{.PRINTBUS}

\section*{Printing of Bus Signals}
```

.PRINTBUS BNAME [VTH[1]=VAL [VTH2=VAL]]

+ [BASE=OCT|DEC|BIN|HEX] [RADIX=UNSIGNED|2COMP]
.PRINTBUS BNAME [MSB:LSB]|BNAME[MSB:LSB](MSB:LSB)|BNAMEMSB:LSB
+ [BASE=OCT|DEC|BIN|HEX] [RADIX=UNSIGNED|2COMP]

```

This command prints all the bits of a bus, previously defined via the .setbus and using . sigbus to send a value. . setbus can be implicitly declared, providing that BNAME [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used.

\section*{Parameters}
- BNAME

Bus name, previously defined via the .SETBus command, unless BNAME [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used, in which case .SETBUS is implicitly declared.
- VTH[1]=VAL

If a voltage threshold is specified, the bus of an analog signal is plotted as a bus (hexadecimal format), else all the different signals of the bus are plotted separately in the waveform viewer as analog waves. (VTH and vTH1 are equivalent to ensure backwards compatibility.)
- VTH2=VAL

This can be used to plot the indeterminate value as shown below:
When only vтн1 is given:
If value \(<\mathrm{V}\) тн then logic state 0 .
If value \(>\mathrm{V} \boldsymbol{\mathrm { Tm }}\) then logic state 1 .
When both vthi and viriz are given:
If value < vini then logic state 0 .
If VTH1 < value < VTH2 then state X.
If value \(>\) vтн2 then logic state 1 .
- MSB:LSB

Series of bit names, the most significant bit being defined first. This mechanism can be used to implicitly declare .setbus.
- BASE

Keyword indicating that the bus signal number system is to be defined.
оСт
Keyword indicating that bus signals are defined in octal.
DEC
Keyword indicating that bus signals are defined in decimal. Default.

\section*{BIN}

Keyword indicating that bus signals are defined in binary.
HEX
Keyword indicating that bus signals are defined in hexadecimal.
- RADIX=UNSIGNED | 2COMP

Defines how negative values inside bus patterns are managed.
UNSIGNED-negative values are forbidden (default)
2COMP-the two's complement of the value is done

\section*{Examples}

In order to display the output of a bus, you can use the following syntax:
```

.PRINTBUS Y<instance_name> -> <vector_name>

```

The following example shows how a second voltage threshold can be used:
```

.printbus foo vth=1 vth2=4
.checkbus OUT_BUS_2 vth=1 vth2=4 base=bin

+ 1000ps 01
+ 7000ps x
+ 12000ps 11
+ 15000ps 01
+ 19500ps 01
+ 20000ps 10
+ 22000ps 10
+ 30000ps 01

```

Refer to ".CHECKBUS" on page 561 for more information.
.PRINTBUS can be used to implicitly declare . SETBUS, providing that BNAME [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used as shown below:
```

.PRINTBUS SELECT[2:0]
.PRINTBUS DOUT<3:0> VTH=1.65

```
is equivalent to:
```

.SETBUS SELECT SELECT[2] SELECT[1] SELECT[0]
.PRINTBUS SELECT
.SETBUS DOUT DOUT<3> DOUT<2> DOUT<1> DOUT<0>
.PRINTBUS DOUT VTH=1.65

```

The following example shows the most significant bit as 1 and the least significant as 5 , where the bus name is foo.
```

.PRINTBUS foo1:5 vth=3

```

Example .chi file extract for .PRINTBUS FILTWD_IN BASE=BIN:
\begin{tabular}{ll} 
1: BUS (FILTWD_IN) \\
TIME & 1 \\
X & \\
& \\
0.0 & 0001 \\
\(1.0000 \mathrm{E}-07\) & 0001 \\
\(2.0000 \mathrm{E}-07\) & 0001 \\
\(3.0000 \mathrm{E}-07\) & 0001 \\
\(4.0000 \mathrm{E}-07\) & 0001 \\
\(5.0000 \mathrm{E}-07\) & 0001 \\
\(6.0000 \mathrm{E}-07\) & 0001 \\
\(7.0000 \mathrm{E}-07\) & 0001 \\
\(8.0000 \mathrm{E}-07\) & 0001 \\
\(9.0000 \mathrm{E}-07\) & 0001 \\
\(1.0000 \mathrm{E}-06\) & 0000 \\
\(1.1000 \mathrm{E}-06\) & 0010 \\
\(1.2000 \mathrm{E}-06\) & 0010 \\
\(1.3000 \mathrm{E}-06\) & 0010 \\
\(1.4000 \mathrm{E}-06\) & 0010 \\
{\([. .0]\)} &
\end{tabular}

\section*{.PRINTFILE}

\section*{Print Tabular Output File}
```

.PRINTFILE [ANALYSIS] OVN FILE=filename [STEP=value]

+ [START=value] [STOP=value] [FORMAT=DATA]

```

This command defines the contents of a tabular listing of any number of output variables, and dumps them to the specified file in ASCII format or as a . DATA statement. Multiple .PRINTFILE commands can share an output file, with variables being added one after the other, or multiple files can be defined.

The number of decimal places in the output of .PRINTfile changed between Eldo v6.7 and v6.8 from six to five. It became linked with option NUMDGT, which has a default value of 5 . For backward compatibility, set option NUMDGT to 6 .

\section*{Parameters}
- ANALYSIS

Optional. Specifies the analysis type, which can be useful in the case of multiple types of analysis in the .cir file. Can be one of the following:
dC|DCSWEEP
Specifies that the plots are required for a DC analysis.
AC
Specifies that the plots are required for an AC analysis.
TRAN
Specifies that the plots are required for a transient analysis.
NOISE
Specifies that the plots are required for a noise analysis.
SSTAC|SSTXF|SSTNOISE|SSTJITTER|TMODSST|FMODSST|FOURMODSST|TSST| FSST|SSTSTABIL
Please refer to the Display Command Syntax chapter of the Eldo RF User's Manual for more information regarding these RF options.

FOUR
Outputs FFT results. See "FOURxx (label_name)" on page 799 for display options.

DSP
Outputs DSP results. See "DSPxx (label_name)" on page 799 for display options.

\section*{SWEEP}

Specifies that the plots are required during a multiple-run simulation if defined.
- OVN

Output variable name. The syntax for specifying the list of plot specifications to be monitored is provided in "Plot Specifications (OVN)" on page 799. Mandatory.
- FILE=filename

Specifies the file name which the table will be printed.
- \(\operatorname{STEP}=\) value

Performs a sampling of the variable(s). If this parameter is specified in more than one .PRINTfile command using the same output file then the smallest value for Step is used. It can only be specified for databases that support multiple x -axes in the same simulation, for example JWDB. Other databases will ignore this parameter.
- START=value

Defines the first x -axis value that must be printed in the output file.
- \(\quad\) STOP=value

Defines the last x -axis value that must be printed in the output file.
- FORMAT=DATA

When specified, the output of .PRINTfile will be saved as a .DATA statement.
Related options
NUMDGT (see "NUMDGT=INTEGER_VAL" on page 996)

\section*{Examples}
```

.printfile tran v(1) i(r1) file="output.txt"

```

This example requests that the voltage on node 1 and the current through r1 be printed to the file output.txt.
```

.step param vdd 1 5 1
.step param vbb 2 6 2
.extract dc label=p1 pval(vdd)
.extract dc label=p2 pval(vbb)
.extract dc label=m1 i(r1)
.printfile sweep meas(p1) meas(p2) meas(M1) file=foo.txt format=data

```

This example specifies the output of .PRINTFILE will be saved as a .DATA statement. File foo.txt will contain:
```

.DATA dataname MEAS (P1) MEAS (P2) MEAS (M1)

+ 1.000000e+00 2.000000e+00 5.000000e-01
+ 1.000000e+00 4.000000e+00 2.500000e-01
+ 1.000000e+00 6.000000e+00 1.666667e-01
+ 2.000000e+00 2.000000e+00 1.000000e+00
+ 2.000000e+00 4.000000e+00 5.000000e-01
+ 2.000000e+00 6.000000e+00 3.333333e-01
+ 3.000000e+00 2.000000e+00 1.500000e+00
+ 3.000000e+00 4.000000e+00 7.500000e-01
+ 3.000000e+00 6.000000e+00 5.000000e-01
+ 4.000000e+00 2.000000e+00 2.000000e+00
+ 4.000000e+00 4.000000e+00 1.000000e+00
+ 4.000000e+00 6.000000e+00 6.666667e-01
+ 5.000000e+00 2.000000e+00 2.500000e+00
+ 5.000000e+00 4.000000e+00 1.250000e+00

```
```

+ 5.000000e+00 6.000000e+00 8.333333e-01
. ENDDATA

```

Below is another example where the output of .PRINTfile will be saved as a .DATA statement.
```

.tran 1n 10n
.defwave tran foo=xaxis
.printfile tran w(foo) I(rl) file=foo2.txt format=data

```

File foo2.txt will contain:
```

.DATA dataname W(FOO) I(R1)

+ 0.000000e+00 0.000000e+00
+ 5.000000e-12 1.500000e-03
+ 1.500000e-11 4.500000e-03
+ 3.500000e-11 1.050000e-02
+ 7.500000e-11 2.250000e-02
+ 1.550000e-10 4.650000e-02
+ 3.150000e-10 9.450000e-02
+ 6.350000e-10 1.905000e-01
+ 1.275000e-09 3.825000e-01
+ 2.555000e-09 7.665000e-01
+ 5.115000e-09 1.534500e+00
+ 1.000000e-08 3.000000e+00
. ENDDATA

```

\section*{.PROBE}

\section*{Output Shortform}
```

.PROBE [ANALYSIS] [ALL|I|IX|ISUB|PORT|PRINT|Q|S|SG|SPARAM|V|VN |VTOP |

+ VX|VXN |W |WTOP] [MASK=mask_name] [EXCEPT=pattern] [PRINT] [STEP=val]
+ [DELTA=val]
.PROBE [ANALYSIS] [MASK=mask_name] [EXCEPT=pattern] [alias_name=] OVN
+ [PRINT] [STEP=val] [DELTA=val]

```

At first glance, the difference in using the . Probe syntax above instead of using the .Print command may not be clear. When using .PRINT, simulation results are written to the .chi log file in ASCII format. When using . Probe, the set of signals to be monitored is specified in the same way, but results are written to binary output files (.wdb). The . \(w d b\) format is the binary format used by EZwave. Thus, the simulated results are available for post-processing. Other advantages are binary storage saves significant disk space and is faster to read/write. .PROBE and . РLOT both dump waves to a database but . PLOT also adds some information for "plot combinations," which means the ability to group waves into graphs, use Smith charts, change wave representation (scattered, histogram, and so on).

Many different simulation results can be created by Eldo. The simulator can output simple node voltages, but also currents through devices, currents through device or subcircuit pins, power quantities, S parameters, internal variables from device models, and so on. All these results are direct raw results from a simulation. The following information, together with the tables shown in "Plot Specifications (OVN)" on page 799, indicate the exact syntax to use for each category. For example:
```

.PROBE TRAN V(OUT)
.PROBE DC ISUB(XBIAS.VOUT)

```

The . Probe command, without specified parameters, forces Eldo to save all node voltages in the binary output file. The . Probe command is a short way of specifying that all nodes should be output. It is not possible to mix analysis types in one command line syntax, therefore the following statement will be rejected:
```

.probe ac I dc V tran I V S

```

It is also not possible to mix in one command line syntax general probe commands (such as . PRobe v, . PROBe I, . Probe vtop) with specific probe commands (such as . Probe v(a)). Two separate commands must be specified.

When the circuit has more than 1000 nodes, . probe is ignored unless the Limprobe parameter, which specifies the maximum number of nodes which may be probed, is increased using the . OPTION command.

\section*{Note}

The saving of all or large numbers of nodes can generate very large output files.

In order to analyze simulation results for huge circuits, and in case the user is only interested in displaying part of the circuit, a .Probe command with nodes defined via both hierarchy and wildcard characters is available. The wildcard (*) may be used to select any list of items for probing quantities such as voltage or current.

Subcircuit instances can be specified for keywords \(\mathbf{v}\), s, w, vx, Ix and isub. A specific subcircuit node can be referenced or wildcards (*) can be used. For example, the below specifies that the node x 1.1 will be probed.
.PROBE TRAN V(X1.1)
In the following example all nodes in subcircuit x 1 will be probed.
. PROBE TRAN V (X1.*)
See also "Using Wildcards in Subcircuit Instances" on page 843. Wildcards, masks, and so on, can be specified for both voltages and currents.

\section*{Parameters}
- ANALYSIS

Optional. Specifies the analysis type, which can be useful in the case of multiple types of analysis in the .cir file. Can be one of the following:

AC
Specifies that the probes are required for an AC analysis.
DC
Specifies that the probes are required for a DC analysis.

\section*{TRAN}

Specifies that the probes are required for a transient analysis.
NOISE
Specifies that the probes are required for a noise analysis. If specified without any other arguments, the noise of all devices will be written to the output file for viewing. For more information on the use of inoise and onoise for printing the equivalent input noise and output noise, see the example in ".NOISE" on page 744 and "ONOISE" on page 813.
SSTAC|SSTXF|SSTNOISE|SSTJITTER|TMODSST|FMODSST|TSST|FSST|SSTSTABIL
Please refer to the Display Command Syntax chapter of the Eldo RF User's Manual for more information regarding these RF options.
Without any analysis specified, the default behavior of Eldo for managing . Probe is to generate the requested probes for all analyses. Since this can generate very large databases in Eldo RF, a default analysis is chosen and a warning printed. For the .SST command, the default analysis is FSST. For the .modsst command, the default analysis is FMODSST.

\section*{DSP}

Displays DSP results. See "DSPxx (label_name)" on page 799 for display options.
- ALL

Specifies that all defwaves, voltages, currents and digital quantities are probed. This is equivalent to specifying . PROBE w + . PROBE v + . PROBE I + . PROBE \(S\).
- I

Causes all currents to be saved (node voltages are not saved).
- IX

Probes the current flowing in and out of all nodes of all subcircuits. Subcircuit instances can be specified for this parameter.
- ISUB

Equivalent to . Probe ix except that the subcircuit pins are printed instead of indexes, for example ( \(\mathbf{X 1 . A}\) ). Subcircuit instances can be specified for this parameter.
- PORT

Specifies that all voltages and digital quantities are probed. This is equivalent to specifying
. PRobe v + . PROBE SG.
- PRINT

Probed defwaves, voltages, currents and digital quantities are printed to both the binary output (.wdb) and ASCII (.chi) files. Equivalent to specifying .probe all print.
- 2

Equivalent to s. Causes all digital quantities (VHDL, VHDL-AMS, Verilog and Verilog-AMS) to be saved. Subcircuit instances can be specified for this parameter.
- s

Causes all digital quantities (VHDL, VHDL-AMS, Verilog and Verilog-AMS) to be saved. Subcircuit instances can be specified for this parameter.
- SG

Saves all digital signals.
- SPARAM

Forces Eldo to dump all S parameters in the output file. Only analyses that are in the frequency domain can be specified, for example AC, SSTAC or \(\operatorname{FSS}\). For more information on S parameters see "Working with S, Y, Z Parameters" on page 1041.
- \(\mathbf{v}\)

Causes all node voltages to be saved-this is the default option. Subcircuit instances can be specified for this parameter.

\section*{- VN}

Only probes node names that are not numbers. The purpose being that nodes named with letters come from the designer, while nodes named with numbers come from an automatic netlister and typically designers wish to only see their own explicitly named nodes. The rule is applied only on the last part of hierarchical node names.
- Vtop

Displays all top level node voltages. The functionality for current is not available (ITOP not allowed).
- vx

Probes voltages on all nodes including all nodes of all subcircuits in the netlist. Subcircuit instances can be specified for this parameter.
- vxn

Equivalent to . Probe vx except that the subcircuit pins are printed instead of indexes, for example (x1.x2.c).
- w

Causes all defwaves to be printed in output files. Subcircuit instances can be specified for this parameter.
- WTOP

Probes defwaves at the top level and dumps them to the output file (not defwaves defined in .subckт commands).
- MASK=mask_name

Pattern filter to mask specific terminal names (node or device) from global . PRobe commands or . Probe commands using wildcards. The rule is applied only to the leaf name of an output specification (voltage or current). Wildcards are allowed. Multiple mAsk specifications are allowed, but multiple strings are not. Example:
```

.probe tran mask=n* v

```

Masks all terminal nodes or devices that start with n .
```

.probe tran V MASK="I" MASK="J"

```

Masks all nodes with leaf names I or J.
- EXCEPT=pattern

Pattern filter to mask specific output names from global .PROBE commands or .PROBE commands using wildcards. This rule is applied to the complete output name, hierarchy included, of an output specification (voltage or current). Wildcards are allowed. Multiple except specifications are allowed, but multiple strings are not. Examples:
```

.probe tran except=x1.x2.n* v

```

Excludes all voltage waveforms whose full pathname starts with x1.x2.n.
```

.probe tran except=N_** v

```

Excludes all voltage waveforms whose full pathname starts with N_.
```

.probe tran except=*x* v

```

Excludes all voltage waveforms related to hierarchical nodes.
```

.probe tran V EXCEPT="X*" EXCEPT="R*"

```

Excludes all nodes with names beginning with X or R .
- PRINT

The probed output will be printed in the .chi file, as well as the binary output file (.wdb). The first example below shows that voltages for an AC analysis are printed in the .wdb and .chi files. In the second case, transient probe results are printed in the . \(w d b\) and .chi files.
```

.PROBE AC V PRINT
.PROBE TRAN PRINT

```

\section*{Note}

To print information to an ASCII file (.chi), without printing in the binary output file (. \(w d b\) ), use the . PRINT command.
- alias_name

Refers to the wave name in the ASCII and binary output files. The alias_name will be the legend displayed inside the wave viewer for the plotted wave as specified by the plot specifications in ovn.
- ovn

Output variable name. A list of plot specifications can follow. Mandatory. The syntax for specifying the list of plot specifications to be monitored is provided on "Plot Specifications (OVN)" on page 799. The syntax is separated into a number of sections depending on the device: MOSFET, BJT, JFET, DIODE, with a common section afterwards.

\section*{Note}

The plot specifications must match the corresponding analysis type, that is, Ac, DC, TRAN, or NOISE.
```

DSPxx(label_name)

```

Displays DSP results. Should be specified as part of ovn. xx can be DB, R, I, P, m, GD (see above).
- STEP=val

Performs a sampling of the waveform(s). A point is dumped every val. It can only be specified for databases that support multiple x -axes in the same simulation, for example JWDB. Other databases will ignore this parameter.
- DELTA=val

Reduces the number of points dumped into the output files, thus reducing their size. Default value is 0.0 . A point with a Y-axis difference less than val compared with the previously output point will not be written to the output file. If a point has a Y-axis difference greater than val compared with the previously output point then both this point and the previous simulation point will be written to the output file.

\section*{Using Wildcards in Subcircuit Instances}

The wildcard \(\left({ }^{*}\right)\) may be used to select any list of items for probing quantities such as voltage or current. Subcircuit instances can be specified for keywords \(\mathbf{v}\), \(\mathbf{I}, \mathbf{s}, \mathbf{w}, \mathbf{v x}, \mathbf{I x}\), ISUB and pow. For example, the below specifies that all nodes in subcircuit x 1 will be probed:
.PROBE TRAN V(X1.*)
The example below will store all currents in devices internal to the Xbias instance:
.PROBE TRAN I(Xbias.*)
The syntax below can be used to specify wildcards in subcircuit instances:
\[
\begin{array}{l|l|l|l|l|l|l|ll}
\mathbf{V} & \mathbf{I} & \mathbf{S} & \mathbf{W} & \mathbf{V X} & \mathbf{I X} & \text { ISUB } & \text { POW(<instance_name>.*), or } \\
\mathbf{V} & \mathbf{I} & \mathbf{S} & \mathbf{W} & \mathbf{V X} & \mathbf{I X} & \text { ISUB } & \text { POW(<instance_name>->*) }
\end{array}
\]

When specifying parameters \(\mathbf{v}, \mathbf{I}, \mathbf{v x}, \mathbf{I x}\), ISUB, POW with a subcircuit instance the -R flag can also be specified. Its usage is shown below.
.PROBE TRAN V(X1.*)
This command will probe all the nodes of subcircuit x 1 but will not probe internal nodes of the subcircuit hierarchy.
. PRobe tran -R V(X1.*)
When specifying the -R flag all internal and external nodes of subcircuits beginning with the name x 1 will be probed. (This can also be performed using the vx keyword.)
. PROBE TRAN -Rn V(X1.*)
Probe all nodes of subcircuit x 1 and enter inside the n level of hierarchy under x 1 for plotting nodes. If n is 0 this specifies the top level.
. PROBE TRAN -R LEVEL=n V(X1.*)
Equivalent to -Rn . Probe all nodes of subcircuit x 1 and enter inside the n level of hierarchy under x 1 for plotting nodes. If n is 0 this specifies the top level.

\section*{Note}
. PROBE TRAN \(\mathrm{V}(\mathrm{X1.*}\) ) is equivalent to: . PROBE TRAN -R0 \(\mathrm{V}(\mathrm{X1.*})\)
vx, Ix and isub can be used to probe voltages and currents on all subcircuit input nodes within the hierarchy. For example:
. PRobe tran IX(X1.*)
Here the current will be probed across all input nodes of subcircuits beginning with the name x 1 .

Defwaves and digital quantities can also be probed for subcircuit instances using wildcards.
. PROBE TRAN S(x1.y1->*)
In this example all internal states (denoted by the syntax "->") of macromodel y1 inside subcircuit x 1 will be probed.
. PROBE TRAN W(x1.*)
This example all defwaves will be probed for subcircuits beginning with the name x 1 .

If the name used in a .PROBE contains square brackets, "[" and "]", these are interpreted as special characters when the wildcard character " \(*\) " is used (see Table 10-31). According to Unix convention, these special characters may be overridden by using the delimiter backslash character " " which removes the special function of the character that immediately follows it. For example, the following only returns names that begin with \(\mathrm{x} 1 . \star\), because, according to Unix convention, \(\mathrm{x}[1]\). * means "all names beginning with " X " and followed by the character "1"":
```

.PROBE tran V(X[1].*)

```

Therefore, to display all nodes beginning with \(\mathrm{V}(\mathrm{X}[1] . *)\) either of the following should be used:

> .option NOCMPUNIX
.PROBE tran V(X[1].*)
or:
```

.PROBE tran V(X$$
1
$$.*)

```

The following table contains a listing of the special characters that can be used with the .PROBE command.

Table 10-31. Special Characters
\begin{tabular}{|l|l|}
\hline Character & Description \\
\hline\(*\) & Matches any sequence of characters. \\
\hline\(?\) & Matches any single character. \\
\hline\([\) abcd \(]\) & Matches any character in the specified set. \\
\hline\([\)-abcd \(]\) & \begin{tabular}{l} 
Matches any character in the specified range, for example \([\mathrm{A}-\mathrm{Z}]\) \\
matches all alphabetical characters.
\end{tabular} \\
\hline
\end{tabular}

Table 10-31. Special Characters
\begin{tabular}{|l|l|}
\hline Character & Description \\
\hline\([!\) abcd \(]\) & \begin{tabular}{l} 
Matches any character not in the specified set, for example \\
{\([!0-9]\)}
\end{tabular} \\
\hline
\end{tabular}

\section*{Signal Monitoring Specifications used with .PROBE Only}
\[
\begin{array}{ll}
\mathrm{V}(\mathbf{X n n} . *) & \text { Monitors the voltage on all of the nodes of subcircuit } \mathbf{X n n} . \\
\mathbf{S}(\mathbf{X n n} . *) & \text { Monitors the states on all of the nodes of subcircuit } \mathbf{X n n} . \\
\mathbf{S}\left(\mathbf{X n n} . \mathbf{Y n n}_{\mathrm{n}}>_{* *}\right) & \begin{array}{l}
\text { Monitors the states on all of the nodes of macromodel } \\
\mathbf{X n n} . \mathbf{Y n n} .
\end{array}
\end{array}
\]

\section*{Examples}
```

*.OPTION description
.option limprobe=1550
...
r1 n30 n400 1k
c1 n490 n610 5p
.probe

```

Specifies that all node voltages will be saved in the <circuit_name>.wdb file. The circuit has more than 1000 nodes, hence the inclusion of the limprobe parameter in the .option command.
```

* Circuit description
r1 n3 n40 1k
.probe I

```

Specifies that all currents will be saved in the <circuit_name>.wdb file.
```

.TRAN 1n 10n
.AC dec 10 1k 10k
.probe

```

Specifies that all node voltages for each analysis specified (that is, transient and AC) will be saved in the <circuit_name>.wdb file. The above .probe is equivalent to the following two statements:
```

.probe TRAN V
.probe AC V

```

The following example specifies to probe all nodes of subcircuit \(\times 1\) :
```

.probe TRAN V(x1.*)

```

The following example specifies to probe all internal states of macromodel \(\mathrm{x} 1 . \mathrm{y} 1\) :
```

.probe TRAN S(x1.y1->*)

```

The following syntax will display all nodes of subcircuit instance \(x 1\) with " 2 " at the end of the node name:
```

.probe TRAN V(x1.*2)

```

Probe requests such as \(I\left(Q^{*} . C\right)\) as well as ic ( \(q^{*}\) ) are accepted. The same applies for extensions B, E and S for BJT, and S, D, G, B for MOSFET.

The following syntax will display nodes in x 1 at hierarchical levels 1 and 2:
```

.probe TRAN v(x1.[!x]*)
.probe TRAN v(x1.x*.[!x]*)

```

In the following example, the wave \(\mathrm{v}(\mathrm{X} 1 . \mathrm{X} 2 . \mathrm{X} 3 . \mathrm{X} 4 . \mathrm{OUT})\) will be plotted inside EZwave, but the legend will be w1 and not \(\mathrm{v}(\mathrm{X} 1 . \mathrm{x} 2 . \mathrm{x} 3 . \mathrm{x} 4.0 \mathrm{UT})\) :
```

.probe TRAN w1=v(X1.X2.X3.X4.OUT)

```

The following specifies values according to the following: \(\mathrm{Vx}(\mathrm{M1} .7)\) refers to the intrinsic source voltage, \(\mathrm{Vx}(Q 1.3)\) refers to the extrinsic emitter voltage, \(\mathrm{VX}(\mathrm{R1.2}\) ) refers to the 'second' pin of resistor R1.
```

.probe VX(M1.7)
.probe VX(Q1.3)
.probe VX(R1.2)

```

In the following example, the current on all pins of all x instances will be recorded. Wildcards do not have to be specified.
```

.probe IX

```

In the following example, the mask will be exclusively applied to all nodes of the instances x1 and x 3 . Instance x 2 will not be masked and the nodes of x 2 will be probed.
```

.probe tran mask=in V(X1.*) V(X3.*)
.probe tran V(X2.*)

```

The following example shows option vxprobe used with a . Probe. Nodes v(1), v(2), \(\mathrm{v}(\mathrm{x} 1 . \mathrm{b}), \mathrm{v}(0), \mathrm{v}(\mathrm{x} 1 . \mathrm{a})\) and \(\mathrm{v}(\mathrm{x} 1 . \mathrm{c})\) will be probed. Without this option only \(\mathrm{v}(1), \mathrm{v}(2)\) and \(\mathrm{v}(\mathrm{x} 1 . \mathrm{b})\) would be probed.
```

.subckt foo a c
r1 a b 1k
r2 b c 1k
.ends foo
v1 1 0 dc 1
x1 1 2 foo
r1 2 0 1
.tran 1n 10n
.probe tran v
.option vxprobe

```

In the following examples, the current on node 2 of voltage source v1 will be probed, and the current on the first node of resistor R1 will be probed.
```

.PROBE TRAN I (V1.2)
.PROBE TRAN I (R1.1)

```

The example below stores currents in devices on top:
.PROBE TRAN I(*)
The example below will store all currents in devices internal to the X1 instance:
. PROBE TRAN I (X1.*)
The example below shows how to reduce the number of points dumped; points separated by less than 0.1 V will not be written in the output files:
.PROBE TRAN V(S) delta=0.1

\section*{.PROBEBUS}

\section*{Printing of Bus Signals}
```

.PROBEBUS BNAME [VTH[1]=VAL [VTH2=VAL]]
.PROBEBUS BNAME [MSB:LSB]|BNAME[MSB:LSB](MSB:LSB)|BNAMEMSB:LSB

```

This command plots all the bits of a bus, previously defined via the . setbus and using . sigbus to send a value. . Setbus can be implicitly declared, providing that BNAME [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used.

\section*{Parameters}
- BNAME

Bus name, previously defined via the . Setbus command, unless BNAME [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used, in which case .setbus is implicitly declared.
- VTH[1]=VAL

If a voltage threshold is specified, the bus of an analog signal is plotted as a bus (hexadecimal format), else all the different signals of the bus are plotted separately in the waveform viewer as analog waves. (vтн and vтн1 are equivalent to ensure backwards compatibility.)
- VTH2=VAL

This can be used to plot the indeterminate value as shown below:
When only VTH1 is given:
If value < vтн then logic state 0 .
If value \(>\mathrm{V} \boldsymbol{\mathrm { T }} \mathrm{H}\) then logic state 1 .
When both vтн1 and \(\mathrm{vtr} \mathbf{2}\) are given:
If value < vтн1 then logic state 0 .
If vтн1 < value < vтн2 then state X.
If value \(>\mathrm{V}\) тн2 then logic state 1 .
- MSB:LSB

Series of bit names, the most significant bit being defined first. This mechanism can be used to implicitly declare .setbus.

\section*{Examples}

In order to display the output of a bus, you can use the following syntax:
```

PROBEBUS Y<instance_name> -> <vector_name>

```

The following example shows how a second voltage threshold can be used:
```

.probebus foo vth=1 vth2=4
.checkbus OUT_BUS_2 vth=1 vth2=4 base=bin

+ 1000ps 01
+ 7000ps x
+ 12000ps 11

```
```

+ 15000ps 01
+ 19500ps 01
+ 20000ps 10
+ 22000ps 10
+ 30000ps 01

```

Refer to ".CHECKBUS" on page 561 for more information.
.probebus can be used to implicitly declare .setbus, providing that bname [MSB:LSB] or BNAME<MSB:LSB> or BNAMEMSB:LSB syntax is used as shown below:
```

.PROBEBUS SELECT[2:0]
.PROBEBUS DOUT<3:0> VTH=1.65

```
is equivalent to:
```

.SETBUS SELECT SELECT[2] SELECT[1] SELECT[0]
.PROBEBUS SELECT
.SETBUS DOUT DOUT<3> DOUT<2> DOUT<1> DOUT<0>
.PROBEBUS DOUT VTH=1.65

```

The following example shows the most significant bit as 1 and the least significant as 5 , where the bus name is foo.
```

.PROBEBUS foo1:5 vth=3

```

\section*{.PROTECT}

\section*{Netlist Protection}
.PROTECT
This command is used in conjunction with ".UNPROTECT" on page 925 to exclude a section of a netlist from being copied into the output file. Can be specified to control the beginning of the encryption process with the Eldo Encryption tool.

\section*{Example}
```

.PROTECT
vin 2 0 ac 0.5
r1 2 3 5k
c3 3 0 0.1p
.ac dec 10 10e+4 10e+8
.plot ac vdb(3)
.UNPROTECT

```

The lines in a netlist between the two commands . РROTECT and . UNPROTECT are not printed to the output file.

\section*{.PZ}

\section*{Pole-Zero Analysis}
.PZ OV
This command is used in conjunction with an AC analysis. When included in the input file, a special file called <circuit_name>.pz is generated by Eldo. Upon conclusion of the simulation, the Pole Zero post-processor may be activated to extract Pole-Zero data and perform simplification of the results, visualization, and so on.

The poles and zeros are extracted for the transfer function characteristic connecting the input node, specified via the AC analysis command. The output node is specified via the .PZ command.

\section*{Note}

This command works only if there is a single AC input source, otherwise an error will be issued.

\section*{Parameters}
- ov

Request output of the specific node or current through a voltage source to the <circuit_name>.pz file. The syntax for voltage or current output is as follows:
- I (Vxx)

Specifies the current through the voltage source vxx .
- \(\mathrm{v}(\mathrm{N} 1[, \mathrm{~N} 2])\)

Specifies the voltage difference between nodes N 1 and N 2 . If N 2 and the preceding comma is omitted, ground is assumed. In the case of subcircuit nodes, N 1 has the form (Xnn.N1) where \(\mathrm{Xnn}_{n}\) is the subcircuit instance.

\section*{1}

For more details on the Pole-Zero Post-processor, refer to the "Pole-Zero Post-Processor" on page 1121 .

\section*{.RAMP}

\section*{Automatic Ramping}
```

.RAMP DC VAL [SIMPLIFY]
.RAMP TRAN T1 T2 [SIMPLIFY]

```

This command is used when Eldo encounters difficulties finding a DC operating point with the conventional .DC command. There are two options available:
- DC ramping may be performed if the power supplies in a circuit are increased linearly from time 0 , by a fixed voltage step. At each step, a DC operating point is searched up to the maximum power supply voltage.
- Transient ramping may be performed if the power supplies are increased linearly from time 0 to \(\mathrm{T1}\), at which point simulation is continued in the form of a transient analysis. When time т2 has been reached, a DC operating point is searched for by Eldo.

When carrying out Gmin ramping, or DC ramping, there are usually steep discontinuities. Eldo has various algorithms which may pass over these discontinuities, but they are CPU time consuming. When specifying simplify, "simplified" Gmin ramping or "simplified" DC ramping will be carried out. In this case, Eldo will attempt to pass over only two discontinuities, before switching to another algorithm, whereupon it should find a DC algorithm which works better on the design. If DC convergence is not achieved by any other algorithms, Eldo will restart Gmin ramping and DC ramping, but will try to pass over all discontinuities.

Transient ramping is a more powerful way of finding a DC operating point than by using DC ramping, but has the disadvantage of being more time consuming. It is recommended that DC ramping methods be tried first and only when everything else fails use transient ramping. The . RAMP TRAN emulates a sweep on all of the input signals. On completion of the sweep, Eldo performs a DC analysis to ensure that the solution found at the end of the transient analysis is Steady-State.

If the keyword simplify is specified at the end of the .ramp command, the last DC analysis will not be performed. If a .TRAN command is specified, the transient simulation will start from the values obtained at the end of the .RAMP TRAN. This is for cases where the user is not interested in the DC, but wishes to use a time constant for increasing transient input voltages without having to change the input signal of the design.

The DC ramping option, . RAMP DC by default, works in conjunction with . OPTION GRAMP. If GRAMP is set to 0 , only . RAMP DC is active. When GRAMP and . RAMP DC are used together, efficiency is improved. See .OPtion "GRAMP=VAL" on page 985.

The conductance value that is placed in parallel with all PN junctions of all devices, and drain and source nodes of MOSFET models also changes in accordance with its defined value with the variation of the DC sweep. If DC source ramping only is desired, you must set GRAMP=0 explicitly.

\section*{Parameters}
- DC

Keyword indicating that DC ramping should be performed.
- tran

Keyword indicating that transient ramping should be performed.
- val

Voltage step at which DC ramping is carried out in volts. The ramping process increases the DC source from 0 up to the nominal value. VAL is the largest step that can be used. The default value is 0.1 V .
- SIMPLIfy

Eldo will attempt to pass over two discontinuities, before switching to another algorithm, more suited to the design.
- T1

The time at which simulation should be continued. The default value is \(1 \mu \mathrm{~s}\).
- T2

The time at which the DC operating point is searched for. The default value is 10 s .

\section*{Related options}
"GRAMP=VAL" on page 985, "GNODE" on page 1016, "PSTRAN" on page 1017, "DPTRAN" on page 1017,

\section*{.RESTART}

\section*{Restart Simulation}
```

.RESTART FNAME [FILE=WNAME]
.RESTART ["fileBasename"] [NEWEST|LONGEST|TIME=VALUE] [FILE=WNAME]

```

This command restarts a simulation run with information previously saved using either the . Save or .tsave command. When a simulation is rerun with .restart, Eldo looks for a .iic or .sav file by default. A .iic file is the default extension when saving a simulation run with the .SAVE or .TSAVE command. A .sav file is created when a simulation run is interrupted by the user with Ctrl-c. See ".SAVE" on page 857 and ".TSAVE" on page 916.

If there is a mismatch between the actual design and the content of the file when reading back a . RESTART file for starting a new TRAN simulation, an error will be returned rather than a warning, and the simulation will stop. That means that the restart command is recommended for a simple transient simulation only.

For more details, refer to the section ".SAVE, .USE \& .RESTART" on page 1080 in the Speed and Accuracy chapter.

In the case of .tran and .REStART associated with a .Step, .mC, .WCASE or .nOISETRAN, the same restart file will be used for all runs, see "Usage of .RESTART and .TRAN with .NOISETRAN, .MC, .WCASE, .STEP" on page 856 for further information.

\section*{Parameters}
- FNAME

Filename containing simulation information which should be used to restart a simulation run.
- FILE=WNAME

Name of file containing the previous .cou or . \(w d b\) file. When this is provided, Eldo concatenates the old and the new binary data files. Binary files can be both .wdb and .cou. The file format is selected by the file extension, which must match the binary file format. FILE= is required.
- "fileBaseName"

Specifies the root name of the .iic file that will be used to restart the simulation. Optional. If omitted Eldo will select the .iic that has the same root name as the top-netlist that is, if the top-netlist is called spice-on-top.cir Eldo will select the file spice-on-top_. If Eldo can not find a file with the root name fileBaseName it will be assumed that the filename (FNAME) has been given.
- NEWEST

The simulation will be restarted with the most recently generated .iic file. Optional.

\section*{- LONGEST}

Restarts the simulation using the .iic that was generated at the greatest time point in the simulation. Optional.
- TIME=value

Restarts the simulation from the specified time. If the file does not exist, Eldo will use the file with the closest time. Optional.

\section*{Example}
```

.restart test.sav file=test_previous.wdb

```

In this example, Eldo will create test.wdb as usual, but will first copy test_previous.wdb into test.wdb before adding new points in the test.wdb file. If the file=test_previous. \(w d b\) string is omitted in the .restart command, then the first point in the test. \(w d b\) file will correspond to the time at which simulation actually restarts.

To permit the concatenation of the previous binary output file with the new binary output file, you have to rename it, for example:
Netlist file: test.cir
Output file: test. \(w d b\) (after the first simulation)
Rename this file: test_previous.wdb
Relaunch Eldo with:
.RESTART test.sav file=test_previous.wdb
A new wdb file is created, test. \(w d b\), which is the concatenation of the previous and the current simulation file.
.RESTART "checkpoint" time=10ns

The simulation will be restarted using the .iic file that was saved at the time \(10 n s\) and has the root name checkpoint.
. RESTART LONGEST
The simulation will be restarted using the .iic file that was saved at the latest time point in the simulation. Eldo will select the .iic that has the same root name as the top-design unit that is, if the top-design is called spice-on-top.cir Eldo will select the file spice-on-top_1.0000000E-08.iic.

\section*{Usage of .RESTART and .AC}

If you have in your input deck both of the following commands:
- . RESTART <file_name>, where file_name comes from the results of a TRAN simulation
- . AC ... UIC command
then the .restart will be interpreted as:
.USE <file_name> OVERWRITE_INPUT
1) Refer to the .AC command UIC parameter, see "UIC" on page 540 for more information.

\section*{Usage of .RESTART and .TRAN with .NOISETRAN, .MC, .WCASE, .STEP}

In the case of .tran and . Restart associated with a .Step, .mC, .WCASE or .nOISETRAN, the same restart file will be used for all runs, for example:
```

.MC 5
.TRAN
.SAVE TIME = ...
.END

```

In this example you would assume that six restart files would be generated (five MC and one nominal), and that in subsequent commands:
```

.MC 5
.TRAN
.RESTART
. END

```
each run would use its "restart file ancestor".
However, this is not how it works. Eldo will use only the latest "restart file" which has been generated for all runs, and unless explicitly specified, Eldo will create a restart file only for the first STEP run or the nominal MC run.

\section*{.SAVE}

\section*{Save Simulation Run}
```

.SAVE [[FILE=]FNAME] DC|END|TIME=VAL1 [REPEAT [ALT|SEQ]]

+ [TEMP=VAL2] [STEP=VAL3] [TYPE=NODESET|IC] [LEVEL=ALL|TOP] [CARLO=index]

```

Writes information at specific times during simulation to a file FNAME. If no filename is given, results are saved in <circuit_name>.iic. To restart a simulation run with this information saved, use the .restart command. See ".RESTART" on page 854. Speed and Accuracy chapter.

For saving a simulation run at multiple time points, see ".TSAVE" on page 916.
A warning will be printed if the . Save command cannot be performed.

\section*{Parameters}
- DC

Keyword indicating that the DC part of the simulation should be saved in FNAME. These results may at a later time be used as .nODESET, . IC, or . Guess values for another simulation via the . USE command.
- END

Keyword indicating that the simulation results should be saved after transient analysis has been completed in fNAME. These results may then be used as re-starting values of another simulation via the .RESTART command.
- time

The value of this keyword is the discrete instant in time after the start of simulation that the simulation results should be saved in fNAME. These results may then be used as re-starting values of another simulation via the . Restart command. This option may also be used in conjunction with the repeat parameter (See below).
- val1

Time, in seconds, at which the simulation results should be saved to FNAME. A number, expression, or parameter can be specified.

\section*{Note}

The time option has the same meaning as the . Option SAVETIME=VAL command, except that the former specifies simulation time and the latter specifies actual CPU time in hours.
- FILE

Optional; used to set the name of the output file.
- FNAME

Filename and extension into which simulation information is written. Filename is alphanumeric but must start with an alpha (letter).
- REPEAT

Keyword, used in conjunction with the time, ALT and SEQ options. When selected, Eldo saves the status of the simulation at every time interval VAL1 to FNAME in accordance with the ALT and SEQ parameters described below. ALT is the default if neither are specified.
- alt

Used in conjunction with repeat to create the files fname.a, fname.b, fname.a, ... in an alternating order, thus overwriting the previous file of the same extension and resulting in only two files fname.a and fname.b being created. Default when repeat is specified.
- SEQ

Used in conjunction with repeat to create the files fname.1, fname.2, fname.3, . . FNAME.N, in a sequential manner, thus creating \(N\) files depending on the values of time and REPEAT.
- TEMP

Keyword indicating that data should be saved to FNAME depending on temperature.
- VAL2

Temperature, in degrees, at which the circuit data should be saved to fNAME.
- Step

Keyword, used in conjunction with the . Step param command. When selected, Eldo saves the status of the simulation to FNAME if the parameter value specified in the .STEP command is equal to a specified value.
- VAL3

Value at which the status of the simulation should be saved to FNAME when equal to the parameter value specified in the .STEP command.

\section*{- type}

Used to set the type of information being dumped. Eldo will generate a Spice-format file which can be loaded with the commands . LOAD or . INCLUDE for subsequent runs.

If nodeset is specified, then when Eldo reads back the file from a . LOAD command, the node voltage information is consider as being equivalent to a .NODESET command.
If IC is specified, then the node voltage information is considered as being equivalent to a . Ic command.

Specifying type means the file will contain less information than the native Eldo save file (.iic). However, it can be re-used on other Spice-like simulators.
- LEVEL=ALL

All nodes have to be dumped in the file (default).
- LEVEL=TOP

Only top nodes (that is, those which are not inside a SUBCKT) are dumped in the file.
1 The previous three parameters work in conjunction with the .LOAD command, see ".LOAD" on page 698.
- CARLO=index

Save simulation information for a specific run (index) of a Monte Carlo analysis. This is useful for debugging purposes, as it would be possible to restart a specific run from a series of Monte Carlo simulations. The DC value would be re-injected into a single Monte Carlo run (IRUN=index of the .MC command).

\section*{Related options}

SAVETIME (see "SAVETIME=VAL" on page 1015)

\section*{Examples}
```

.save test.ddt dc

```

Specifies that DC analysis results of the current circuit simulation should be written to the test.ddt file.
```

r1 1 2 p2
.step param p2 1k 5k 1k
.save status.ccf step = 4k

```

Causes status of current simulation to be saved in status.ccf file when parameter p2 reaches \(4 \mathrm{k} \Omega\).

\section*{.SCALE}

\section*{Automatic Scaling of Active Devices}
```

.SC[ALE] ELTYPE KEYWORD VALUE [KEYWORD VALUE ...]

+ [ELEMENTS ALL|EXCEPT] [ELNAME1 ELNAME2 ...] [(ELNAME1 ELNAME2)]]
.SC[ALE] ELTYPE KEYWORD VALUE [KEYWORD VALUE ...]
+ MODELS MODNAME1 [MODNAME2 ...]
.SC[ALE] MODTYPE KEYWORD VALUE [KEYWORD VALUE ....]
+ [MODELS ALL|EXCEPT] [MODNAME1 MODNAME2] [(MODNAME1 MODNAME2...)]]
.SC[ALE] P FACTOR=VALUE [SUBCKT=SUBNAME] [INST=INSTNAME]
+ [PARAMS ALL|EXCEPT] [PARAM1 PARAM2 ...] [(PARAM11 PARAM22)]]

```

This command scales device and model parameters of active devices automatically.
The first two syntax shown above are the general forms for devices. The third syntax is the general form for device models. The last syntax is an additional feature for parameter scaling.

\section*{Parameters}
- Eltype

Type of element. One of the following element types:
```

D [LEVEL=n]
Diode
Q [LEVEL=n]
BJT
J [LEVEL=n]
JFET
M [LEVEL=n]
Level-n MOSFET

```
- MODTYPE

Type of model. One of the following model types:
```

DM [LEVEL=n]
NPN [LEVEL=n]
PNP [LEVEL=n]
NJF [LEVEL=n]
PJF [LEVEL=n]
NMOS [LEVEL=n]
PMOS [LEVEL=n]
Diode model
npn BJT model
pnp BJT model
n-channel JFET model
p-channel JFET model
n-channel level-n MOS model
p-channel level-n MOS model

```
- KEYWORD

Any valid element or model parameter or keyword.
- ELEMEnts

Keyword indicating the end of a keyword/value pair list for elements.
- PARAMS

Keyword indicating parameter scaling.
- All

Keyword requesting scaling of all elements or models.
- EXCEPT

Keyword requesting scaling of all elements or models with the exception of the ones listed.

\section*{Limitation}

The element parameters or devices are only scaled at the parsing level.
If a .DC is used on a device element with a scale factor, the device element takes only the value specified by the DC analysis. There is no scaling effect.

\section*{.SELECT_DSPF_ON_NODE}

\section*{Select DSPF on Specified Node}
.SELECT_DSPF_ON_NODE \{NODE\}
Used to force Eldo to select parasitic elements on a specified node when a DSPF file has been included using the .DSPF_INCLUDE command.

This command is ignored when DEV=DSPF is specified on the .DSPF_INCLUDE command.

\section*{Parameters}
- node

Specifies node(s) for which the parasitics given in the DSPF file will be selected.

\section*{Example}
.DSPF_INCLUDE testspf.spf
.SELECT_DSPF_ON_NODE n1 n2
For nodes n1 and n2 parasitics as specified in DSPF file testspf.spf will be selected.

\section*{.SENS}

\section*{DC Sensitivity Analysis}
.SENS OVN \{OVN\}
This command causes a DC sensitivity analysis to be performed. By linearizing the circuit around a bias point, the sensitivities of each of the output variables in relation to all the device values and the model parameters are calculated and output.

This Eldo command is restricted to DC sensitivity analysis. For AC sensitivity analysis, see ".SENSAC" on page 865. For TRAN or SST sensitivity analysis, see ".WCASE" on page 934.

The DC sensitivity analysis will be performed only for the first DC of a DCSWEEP.

\section*{Note}

For MOS, only sensitivity with respect to L and W is implemented. For BJT, Diodes and JFET, sensitivity is implemented with respect to all model parameters.

Device sensitivities are provided for the following types:
- Resistors.
- Independent Voltage and Current Sources.
- Voltage and Current Controlled Switches.
- Diodes and Bipolar Transistors.

\section*{Parameters}
- ovn

Output variable name. Request output of the specific node or current through a voltage source to the <circuit_name>.chi file. Syntax for voltage or current output is as follows:
- \(\mathrm{v}(\mathrm{N} 1[, \mathrm{~N} 2])\) Specifies the voltage difference between nodes N1 and N2. If only N1 is specified, ground is assumed for the second node.
- I(Vxx[, Vyy])

Specifies the current difference between voltage sources \(\mathbf{v}_{\mathrm{xx}}\) and \(\mathbf{v}_{\mathrm{yy}}\). If only \(\mathrm{v}_{\mathrm{xx}}\) is specified, current through \(\mathrm{V}_{\mathrm{xx}}\) is printed.

\section*{Example}
```

.sens v(2) i(vCc)

```

Specifies a sensitivity analysis to be performed on the voltage at node 2 and on the current through the voltage source vcc. The results of the analysis are listed in the <circuit_name>.chi file.

1 An example of this type of analysis can be found in "Tutorials" on page 1341.

\section*{.SENSAC}

\section*{AC Sensitivity Analysis}
.SENSAC OVN \{OVN\} FREQ=val1[\{, val2\}] [SORT_REL] [SORT_ABS] [SORT_MAX]
This command causes an AC sensitivity analysis to be performed. By linearizing the circuit around a bias point, the sensitivities of each of the output variables in relation to \(\mathrm{R}, \mathrm{L}, \mathrm{C}\) devices present in the design are calculated and written to the output .chi file.

This Eldo command is restricted to AC sensitivity analysis. For DC sensitivity analysis, see ".SENS" on page 863. For TRAN or SST sensitivity analysis, see ".WCASE" on page 934.

Device sensitivities are provided for the following types:
- Resistors
- Capacitors
- Inductors

The output is sorted from the most sensitive to the least sensitive.

\section*{Note}

This command was previously named .ACSENSRLC.

\section*{Parameters}
- ovn

Output variable name. Request output of the specific node to the <circuit_name>.chi file. Syntax for voltage or current output is as follows:
```

V(N1[, N2])

```

Specifies the voltage difference between nodes N1 and N2. If only N1 is specified, ground is assumed for the second node.

I(Vxx[, Vyy])
Specifies the current difference between voltage sources \(\mathbf{v}_{\mathrm{xx}}\) and \(\mathbf{v}_{\mathrm{yy}}\). If only \(\mathbf{v}_{\mathrm{xx}}\) is specified, current through \(\mathrm{v}_{\mathrm{xx}}\) is printed.
- FREQ

List of frequency values at which the sensitivities must be computed.
- SORT_REL

Used to filter the output. Only devices with a contribution to the output greater than the value: SORT_RELX<MAX_variation_on_output> will be listed. The default value of SORT_REL is 0.001 , which means that all devices contributing to more than \(1 / 1000\) of the maximum variation will be listed.
- SORT_ABS

Used to filter the output. Specifies the absolute threshold, below which contributors will not be listed. Default value is 0 .
- SORT_NBMAX

Used to filter the output. Allows the user to limit the list of contributors to a certain value. By default, all contributors are listed.

Note \(\qquad\)
The sorting parameters are additive, that is, their respective effects are cumulative. For example, to create a report with only devices contributing to \(10 \%\) or more of the maximum output deviation and have 15 contributors at most you would specify:
SORT_REL=0.1
SORT_NBMAX=15

\section*{Example}
```

v1 1 0 ac 1
rv1 1 0 1
e1 2 0 1 0 1000
r1 2 0 1k
r2 2 3 1k
r3 3 4 1k
c1 4 0 100n
r4 4 0 1k
.ac dec 20 10 1giga
.extract ac yval(vm(3),10k)
.sensac v(3) freq=10k

```

Specifies a sensitivity analysis to be performed on the voltage at node 3 at a frequency of 10 kHz . The results of the analysis are listed in the <circuit_name>.chi file, example results:
```

.SENSAC V(3) SORT_REL = 1.000000e-03
Analysis results at 1.0000E+04 Hertz:
ELEMENT
(VOLTS/UNIT) (VOLTS/PERCENT)
C on 4 1.000E-07 -1.94E+08 -1.94E-01

```

\section*{.SENSPARAM}

\section*{Sensitivity Analysis}
```

.SENSPARAM sub[ckt]=subckt_name param=parameter_list

+ [var[iation]=value] [inst[ance]=instance_list]
+ [sort=inc[reasing] | dec[reasing] alpha[betical]]
+ [sort_nbmax=value] [sort_abs=value | sort_rel=value]

```

This command activates a sensitivity analysis of extracts versus subcircuit parameters.
Designers need sensitivity information for design parameters (parameters they can act upon). This command computes the sensitivity of voltages/currents and extracts to these design parameters.

The first simulation is the nominal simulation, using nominal values for the parameters. The following simulations are sensitivity analysis runs where Eldo applies a small variation to one of the \(P\) parameters, keeping all other to their nominal value, and computes the sensitivity of the targets relative to the current parameter. Therefore, there are \(1+\mathrm{P}\) simulations.

The sensitivity results represent the variation of the extracted value for a variation of \(1 \%\) of the parameter value.

\section*{Parameters}
- sub[ckt]

A subcircuit name.
- param

Defines the list of parameters of subcircuit subckt_name for which the sensitivity must be calculated.
- var[iation]

Defines the variation value for the sensitivity parameters. Default is \(0.1 \%\).
- ins[tance]

Defines a list of instances of subcircuit subckt_name. The sensitivity analysis will be restricted to parameters of these instances. This keyword supports standard wildcards: * and ?. For example:
.sensparam subckt=resi instance=x2.* param=a,b variation=7\%
means that all parameters \(a\) and \(b\) of instances of subcircuit resi inside instance X 2 will be subject to sensitivity.
```

.sensparam subckt=resi instance=x2 param=c,e variation=0.03

```
means that parameters c and e of instance x 2 of subcircuit resi only will be subject to sensitivity.
- sort

Defines the ordering method which will be used to print sensitivity results. Default is alphabetical.
- sort_nbmax

Only the specified \(n\) first contributions will be printed.
- sort_abs

Only the contributions greater than the given value in absolute will be printed.
- sort_rel

Only the contributions greater than the given value in relative will be printed.

\section*{Note}

If several . SENSPARAM commands are specified in the netlist, only the last value for keywords sort, sort_nbmax, sort_abs and sort_rel will be retained.

\section*{Example}
```

* .sensparam example
.subckt resi a b param: a=1 b=1 c=1 d=1 e=1
R1 a b r={a+2*b+3*c+4*d+5*e}
.ends resi
.subckt div a b param: a=1 b=1 c=1 d=1 e=1
x1 a 1 resi a=a b=b c=c d=d e=e
x2 1 b resi a=a b=b c=c d=d e=e
.ends div
v1 1 0 sin(0 1 0.5g)
x1 1 2 resi a=2 b=1 c=5 d=6 e=10
X2 1 2 resi a=10 b=2 c=6 d=3 e=1
X3 1 2 div
r2 2 0 1
.sensparam subckt=resi instance=x3.* param=a,b variation=2%
.sensparam subckt=resi instance=x2 param=c,e variation=0.03
.sensparam subckt=resi param=d sort_abs=4e-4
.tran 1n 15n
.extract tran yval(i(r2),5n)
.end

```

The three . Sensparam commands in the above example define which parameters will be used for sensitivity analysis. The first command defines that parameters \(a\) and \(b\) of all instances of subcircuit resi* inside instance X 3 will have a variation of \(2 \%\) applied to their nominal values. The second command defines that parameters c and e of top instance X 2 will have a variation of \(3 \%\) applied to their nominal values. The third command defines that parameter d of all instances of subcircuit resi will have a default variation of \(0.1 \%\) applied, that contributions lower than \(40 \mathrm{e}-9\) will not be printed, and are sorted in decreasing order.

The sensitivity results represent the variation of the extracted value for a variation of \(1 \%\) of the parameter value. See example results below.
\begin{tabular}{|c|c|c|c|c|c|c|}
\hline \multicolumn{2}{|l|}{YVAL (I (R2) , 5N)} & \multirow[t]{2}{*}{NOM :} & \multicolumn{4}{|l|}{5.2297E-05} \\
\hline * & Normalized & & Extract & Parameter & Parameter & Parameter \\
\hline * & Sensitivity & (\%/\%) & Variation (/\%) & Nominal Value & Variation & Name \\
\hline * & 1.1039E-01 & & -5.7732E-08 & \(6.00000 \mathrm{e}+00\) & \(3.000 \mathrm{e}+00 \%\) & X2. C \\
\hline * & \(7.2816 \mathrm{E}-02\) & & -3.8081E-08 & \(3.00000 e+00\) & 1.000e-01\% & X2.D \\
\hline * & \(6.4746 \mathrm{E}-02\) & & -3.3860E-08 & \(1.00000 \mathrm{e}+00\) & \(1.000 \mathrm{e}-01 \%\) & X3. X1. D \\
\hline * & \(6.4746 \mathrm{E}-02\) & & -3.3860E-08 & \(1.00000 \mathrm{e}+00\) & \(1.000 \mathrm{e}-01 \%\) & X3. X2.D \\
\hline * & 4.0429E-02 & & -2.1143E-08 & \(6.00000 e+00\) & \(1.000 \mathrm{e}-01 \%\) & X1.D \\
\hline
\end{tabular}

\section*{.SETBUS}

\section*{Create Bus}
.SETBUS BNAME PN \{PN\}
This command creates a bus BNAME with a number of bits PN.

\section*{Note}

Bus signals are defined using the . sigbus command.

\section*{Parameters}
- BNAME

Bus name.
- PN

Bit name, the most significant bit being defined first. Groups of bits can be specified as a bit range, and Eldo will expand the bus. Suppose i and j are two integers, the expansion rule is as follows:

If \(i<j\), then \(n[i: j]\) is expanded into \(n[i], n[i+1], n[i+2] \ldots n[j]\)
If \(i>j\), then \(n[i: j]\) is expanded into \(n[i]\), \(n[i-1], n[i-2] \ldots n[j]\)
To disable the automatic bus expansion, specify option nosetbusexpand.

\section*{Related option}
nosetbusexpand (see "NOSETBUSEXPAND" on page 956)

\section*{Example}
```

.setbus bus1 p5 p4 p3 p2 p1 p0

```

Specifies a bus bus1 with the pins p5, p4, p3, p2, p1 and p0. Pin p5 is the most significant bit.

The following example shows bus expansion:
```

.setbus foo a[4:2]

```
is equivalent to:
```

.setbus foo a[4] a[3] a[2]

```

The following is another example of bus expansion with multiple bus specifications:
```

.setbus bus2 a[4:2] b1 b[0] a[9:6]

```

Specifies a bus bus2 with a[4], a[3], a[2], b1, b[0], a[9], a[8], a[7] and a[6].

\section*{.SETKEY}

Set Reliability Model Key (Password)
.SETKEY [MODEL=model_name] KEY=key_value
This reliability analysis command defines a key (password), which is associated to a specific model or to all the models of a library.

For the complete description of this command and information on all reliability commands, see the separate chapter Reliability Simulation.

\section*{.SETSOA}

\section*{Set Safe Operating Area}
```

.SETSOA [LABEL="STRING"] [ANALYSIS] [SOACODE=val]

+ E {EXPRESSION=(MIN,MAX[,XAXIS])}
.SETSOA [IABEL="STRING"] [ANALYSIS] [SOACODE=val]
+ E IF (EXPR) THEN({PARAM=(MIN,MAX[,XAXIS])})
+ ELSE ({PARAM=(MIN,MAX[,XAXIS])}) ENDIF
.SETSOA [LABEL="STRING"] [ANALYSIS] [SOACODE=val]
+ E SUBCKT=subckt_list {PARAM=(MIN,MAX[,XAXIS])}
.SETSOA [IABEL="STRING"] [ANALYSIS] [SOACODE=val]
+ D DNAME [SUBCKT=subckt_list|INST=inst_list] {PARAM=(MIN,MAX[,XAXIS])}
.SETSOA [LABEL="STRING"] [ANALYSIS] [SOACODE=val]
+ D DNAME [SUBCKT=subckt_list|INST=inst_list]
+ IF(EXPR) THEN({PARAM=(MIN, MAX[, XAXIS])})
+ ELSE({PARAM=(MIN, MAX[, XAXIS])}) ENDIF
.SETSOA [LABEL="STRING"] [ANALYSIS] [SOACODE=val]
+ M MNAME [SUBCKT=subckt_list|INST=inst_list] {PARAM=(MIN,MAX[,XAXIS])}
.SETSOA [LABEL="STRING"] [ANALYSIS] [SOACODE=val]
+ M MNAME [SUBCKT=subckt_list|INST=inst_list]
+ IF (EXPR) THEN({PARAM=(MIN, MAX[, XAXIS])})
+ ELSE({PARAM=(MIN, MAX[, XAXIS])}) ENDIF

```

Specifies the safe operating area limits for device parameters (D), model parameters (M) and Eldo expressions (E).

\section*{Caution}


Eldo issues a warning at run time whenever a safe operating limit is violated.

Devices may be selected using either the device name or its model name (if one exists). If limits are specified using both device and model names for a component, then both results are produced. There is no priority selection, and so the particular device must respect all conditions specified to generate no warning (regardless of whether these are the same or different).

Limits set using . Setsoa are checked when the .checksoa command is used, see ".CHECKSOA" on page 564.

This command applies to all types of analysis, as specified, and may also be used in conjunction with .temp, .STEP, .MC, and . WCASE commands. For the last two cases, only a check of the typical case is done. However, if the .mC analysis statement contains the all parameter, the . checksoa will be activated for each Monte Carlo run.

The IF statement used in conjunction with the keywords THEN, ELSE, ENDIF may be used with expressions to specify conditions for when a SOA should be checked.

It is possible inside SOA expressions to refer to device instance or model parameters via its parameter name, such as: D (*, <parameter_name>) or m (*, <parameter_name>). The wildcard character * specifies that Eldo will search for the parameter in the device or model
specified in DNAME or MNAME respectively. Model parameters can be specified for devices and device parameters can be specified for models.

At the top level, a list of subcircuits or instances at a lower level of hierarchy can be specified with devices or models.

The name of a model can be prefixed with X instance or subcircuit names. Therefore the SOA model name should contain the wildcard character * if the SOA should also apply to all of the extended models. For example, if a model attached to XSUBCKT.M1 is NCH.10, and a model attached to XT.MAIN is XT.NCH.10, the statement .SETSOA M NCH will detect that XSUBCKT.M1 has a model valid for checking, not XT.MAIN. For improved name matching, the statement . SETSOA M '*NCH*' should be specified.

This command also accepts an optional label as the first argument. The label will appear in the ASCII output file, which can be useful for readability of this file.

You can use the E(xpressions) parameter to specify a named subcircuit at any part of the hierarchy and set safe operating limits.

A code can be assigned to any SOA check, using the SOACODE parameter. Based on this code you can filter SOA checks to enable/disable in the .checksoa command.

Safe Operating Area warnings can be searched automatically using the following AWK script:
```

\#!/bin/sh
awk '
BEGIN {
found = 0
}
(\$2 ~ /SOA/ \&\& \$3 ~ /INFORMATION/) {
found=1
}
(found==1) {
if (\$1 == "*|")
print \$0
| \$*

```

\section*{Parameters}
- LABEL=" < STRING>"

Specified as the first argument. The label will appear in the ASCII output file, which can be useful for readability of this file.
- ANALYSIS

Optional. By default, it depends on the analysis specified in the netlist. Can be one of the following:

AC
Specifies that the checks are required for an AC analysis.

DC
Specifies that the checks are required for a DC analysis.

\section*{TRAN}

Specifies that the checks are required for a transient analysis.
DCSWEEP
Specifies that the checks are required for a DCSWEEP analysis.
FOUR
Specifies that the checks are required for an FFT analysis.

\section*{TMODSST|TSST|FSST}

Specifies that the checks are required for an RF analysis.
- SOACODE=val

A code assigned to an SOA check. Based on this code you can filter SOA checks to enable/disable in the .CHECKSOA command. The code should be a positive integer quantity.
- EXPRESSION

An expression whose calculated value is to be checked. This can use the same syntax as described in the . Ехтract command, section "FUNCTION" on page 645, for example:
```

.SETSOA E xup(v(out),4,0,100n,1)

+ -xup(v(out),1,0,100n,1) = (*,3n)

```
- DNAME

Name of a device whose parameter(s) are to be checked. The wildcard character * can be used in a device name to specify that all devices of the same type should be checked (for example .SETSOA D \(r^{*} .\). . will check all resistors in the netlist).
- MNAME

Name of a model whose parameter(s) are to be checked. The following device categories can also be specified: NMOS, PMOS, NPN, PNP, NJF, PJF, D, for example:
```

.SETSOA M NPN ...

```
indicates all NPN devices will be checked.
- PARAM

Name of the parameter to be checked for example:
ib, IC, IE, Is, vbe, vbc, vbs, vce, vcs, ves, pow, vc, vs, vb, ve for a bipolar transistor.
ig, is, id, ib, vgd, vgs, vgb, vbs, vbd, vds, pow, vs, vd, vg, vb for a MOS/JFET. vPOS, VNEG (for voltage on positive/negative pin), VDIP, \(I\), for a dipole.
pow for power.
To access the vTh value, use vt (device_name), to access the VDSAT value, use vDSS (device_name).
The wildcard character * can be used for the instance specifier in conjunction with device
categories, for example: VGS (*), VCE (*)
Expressions are also allowed, for example:
. SETSOA M NMOS VGS (*) + VDS(*) = (0,*)
- MIN

Minimum value of expression/parameter to check. SOA limits can also be defined using .DATA statements for expressions.
- MAX

Maximum value of expression/parameter to check. SOA limits can also be defined using .DATA statements for expressions.

Note
Expressions are also accepted in the MIN/MAX boundaries, together with parameters. Specifying * for a MIN/MAX boundary means that the appropriate limit should not be checked.
- XAXIS

Specifies the \(x\)-axis length that must be achieved before SOA warnings are printed.
- IF (EXPR)

Defines an IF statement where EXPR is the expression for the IF condition. The following operators are allowed:
```

|| for OR
\&\& for AND
== for EQUAL
< or <= for INFERIOR and INFERIOR or EQUAL
> or >= for SUPERIOR and SUPERIOR or EQUAL

```

IF statements can be nested. Only the following parameters are allowed in IF expressions: V()\(, \mathrm{I}(), \mathrm{P}(), \mathrm{E}(), \mathrm{M}()\), and EM() .
- then

Defines a THEN statement. Used in conjunction with IF. The user can define a parameter(s) to be checked when the IF statement is true.
- ElSE

Defines an ELSE statement, Used in conjunction with IF and ELSE. The user can define a parameter(s) to be checked if the IF statement is false.
- SUBCKT=subckt_list

Specifies a list of subcircuits to be checked. Valid for the D and \(M\) types.
- INST=inst_list

Specifies a list of instances to be checked. Valid for the D and M types.

\section*{Examples}
```

SOA check
.width out=80
.model n npn
r1 in out 10k
c1 out 0 1p
q1 c b 0 0 n
rl c vdd 1k
vin in 0 pwl 0 0 1n 10 20n 10 21n 100
vdd vdd 0 5
vb b 0 pwl 0 -1 40n 1
.setsoa d r1 i=(*, 3m)
.setsoa m n ic=(-1u, 3m)
.setsoa e IC(q1)/IB(q1)=(*, 100)
.checksoa
.option eps=1u
.tran 1n 40n
.plot tran v(out)
.plot tran i(r1) ib(q1) ic(q1)
.end

```

\section*{Caution}

This produces the following warning on the screen (or in the . log file, if you are simulating in background):
***WARNING: SOA DETECTION: See output file for details

The following results will be obtained in the .chi file:
```

1*******5-Feb-2001 *********** Eldo v5.4
OSOA CHECK
0**** SOA INFORMATION TEMPERATURE = 27.000 DEG C
0****************************************************************
R1:
I(R1)
X AXIS WINDOW: [ 20.32351N 31.73637N ] Value superior to 3.000000e-
0 3

* IC(Q1)/IB (Q1)
X AXIS WINDOW: [ 28.42081N 32.91932N ] Value superior to
1.000000e+02
Q1:
IC (Q1)
X AXIS WINDOW: [ 35.33011N 40.00000N ] Value superior to 3.000000e-
0 3

```

The following is an example of using the optional 3rd boundary XAXIS parameter:
```

.SETSOA D M1 VGS = (1, 2, 3u) VGS = (0, 4, 1u)

```
this means that when VGS is outside the limits \([1,2]\) for a time-period greater than or equal to \(3 \mu \mathrm{~s}\), OR when vgS is outside the limits \([0,4]\) for a time-period greater than or equal to \(3 \mu \mathrm{~s}\) a warning is given.
The optional label specification can be used, as shown in the example below:
```

.setsoa label="My severe error" m ndig

+ Vg(*)-Vb(*)=(-15.0,15.0)
.setsoa label="My warning" m ndig
+ Vg(*)-Vb(*)=(-22.3,22.3)

```

The ASCII output file, with the label appearing, would look similar to the following:
```

* M\#\$I10:
VG(*)-VB(*) LABEL="My severe error"
X AXIS WINDOW: [ 110.00000N 1.00000U ]
Value inferior to -1.500000e+01
VG(*)-VB(*) LABEL="My warning"
X AXIS WINDOW: [ 117.30000N 1.00000U ]
Value inferior to -2.230000e+01

```

The following example shows how the boundary specifications can be used inside SOA.
```

.SETSOA E xup(v(out),4,0,100n,1)

+ -xup(v(out),1,0,100n,1) = (*,3n)

```

Here, SOA notification will appear if the extracted value is higher than \(3 n\).
The following example shows how subcircuit parameters can be used inside SOA.
```

.SUBCKT TEST A B
R1 A B 1k
.SETSOA D R1 V=(-CH,CH)
.ENDS TEST
X1 1 0 TEST CH=25
Vd 1 0 30
.DC vd 10 30 0.1
.PLOT DC i(Vd)
.CHECKSOA
.END

```

The example below shows multiple expressions can be used in a .SETSOA command.
```

.SETSOA E IC(q1)/IB(q1)=(*, 100)

+ xup(v(out),4,0,100n,1) = (*,4n)

```

The following examples show IF statements used in . SETSOA commands.
```

.SETSOA M NMOS IF(D(*,W) < 10U) THEN VGS(*) = (*,1.2) ENDIF

```

In the example above, the VGS parameter on all NMOS transistors with a device parameter w of less than \(10 \mu \mathrm{~m}\) will be checked with respect to a maximum value of 1.2 .
```

.SETSOA M NMOS IF((Id(*) >= 0.1u)\&\&(Vgs(*)>(VT(*)-0.3)))

+ THEN Vds(*) - VDSS(*) = (0,*) ENDIF

```

In the example above, the IF statement sets up the condition that for all NMOS transistors that have a value of parameter Id greater than or equal to 0.1 and parameter vgs is greater than the value computed by VT-0.3, then the value calculated by Vds (*)-VDSS (*) will be checked with respect to a minimum value of 0 .
```

.SETSOA E IF(P1>0) THEN IF(P2>0) THEN V(1)=(*,0.5) ENDIF ENDIF

```

In the example above, if parameter P1 is greater than zero, then the second IF statement will be performed. The second IF statement defines that parameter \(\mathrm{V}(1)\) will be checked with respect to a maximum value of 0.5 if parameter P2 is greater than zero.
```

.DATA vout

+ tt voutmax voutmin
+ 0 0.1 0.0
+ 80n 0.1 0.0
+ 120n 5.0 4.5
+ 200n 5.0 4.5
.ENDDATA
.SETSOA label=vout_correct E v(OUT)=[vout(voutmin),vout(voutmax)]

```

The example above shows how SOA limits can be defined using .DATA commands.
The following example shows how SOA limits can be checked from the top level using wildcards and across instance/subcircuit lists at a lower level of hierarchy.
```

.SUBCKT NHVT D G S B PARAM: W=1.0 L=0.5 xl=0
.MODEL NHVT NMOS LEVEL=53 XL = p1
M1 D G S B NHVT W=W L=L
.ENDS
X1 D G S B NHVT xl = 0.1u
X2 D G S B NHVT
X3 D G S B NHVT

```

Eldo will create internally two models: one named X1.NHVT, used by device X1.M1, and another one named NHVT.NHVT, shared by X2.M1 and X3.M1. If you wish to perform some SOA checks on the model NHVT, specify:
```

.SETSOA M '*.NHVT' VDS=(-1.2,1.2)

```

An equivalent syntax is:
.SETSOA M NHVT SUBCKT=NHVT VDS=(-1.2,1.2)
It will check for VDS on the three instances X1.M1, X2.M1, and X3.M1.
Specifying the following, Eldo will check only for instance X1.M1:
```

.SETSOA M NHVT INST=X1 VDS=(-1.2,1.2)

```

The following shows how to check subcircuits in your netlist using the E(xpression) syntax:
```

.subckt mysub n1 n2
Rend1 n1 3 1k
Rp 3 4 2k
Rend2 4 5 3k
C2 5 n2 .1uf
.ends
.setsoa E subckt=mysub Isub(n1) = (1m, 2m)
.setsoa E subckt=mysub v(n1) = (1, 2)

```
```

.setsoa E subckt=mysub v(n1,n2) = (1, 2)

```

\section*{.SIGBUS}

\section*{Set Bus Signal}
```

.SIGBUS BNAME|BNAMEMSB:LSB|BNAME [MSB:LSB]|BNAME[MSB:LSB](MSB:LSB)

+ [VHI=VAL] [VLO=VAL] [TFALL=VAL] [TRISE=VAL]
+ [BASE=OCT |DEC|BIN|HEX] [SIGNED=NONE| 1COMP | 2COMP]
+ TN VAL {TN VAL} [P]
.SIGBUS BNAME|BNAMEMSB:LSB|BNAME [MSB:LSB]|BNAME[MSB:LSB](MSB:LSB)
+ [VHI=VAL] [VLO=VAL] [TFALL=VAL] [TRISE=VAL] [THOLD=VAL] [TDELAY=VAL]
+ [BASE=OCT|DEC|BIN|HEX] [SIGNED=NONE| 1COMP | 2COMP]
+ PATTERN $(PAT) {$(PAT)} VAL {VAL} [Z]
.SIGBUS BNAME|BNAMEMSB:LSB|BNAME [MSB:LSB]|BNAME[MSB:LSB](MSB:LSB)
+ [VHI=VAL] [VLO=VAL] [TFALL=VAL] [TRISE=VAL] [THOLD=VAL] [TDELAY=VAL]
+ [BASE=OCT|DEC|BIN|HEX] [SIGNED=NONE| 1COMP | 2COMP]
+ FILE=FILE

```

This command sets signals on a bus bname that has been previously defined via the . setbus command. . SETBUS can be implicitly declared, providing that BNAMEMSB:LSB, BNAME [MSB:LSB] or BNAME<MSB:LSB> syntax is used.

In its first form shown above, . SIGbus defines each transition value and the time at which it occurs as a list of TN VAL value pairs. In its second form, all consecutive signal values are listed in order after the pattern keyword, and a hold time specifies the duration of each signal value specified.

Bus values for both the standard and pattern definitions accept exactly the same syntax.
- parameters are denoted \(\$(\mathrm{P})\) or ' P '
- values can be specified with or without double quotes and use the notation HX[...], DX[...], OX[...], and BX[...] to specify in which base this number is given (by default it is the base of the bus). All these notations can be mixed in the same bus definition, for example:
```

.sigbus a[0:7] VHI=3 VLO=0 THOLD=10ns BASE=BIN

+ PATTERN \$(PAT_RAMP) 101 "001" 'PAT2' BX010 "DX123"

```

Parameters can only be strings, except for buses declared with BASE=DEC. This is mandatory to allow sweeps. If this rule is not satisfied, the following message is issued:
```

ERROR 1545: COMMAND .SIGBUS: bus A, parameters of type real can only be
used with buses using base=DEC

```

If the parameter holds a decimal value, the message issued is:
```

ERROR 1544: COMMAND .SIGBUS: decimal non-integer value found in bus A

```

The sweeping of literal (string) parameters is allowed if the parameters do not effect anything but the .sigbus command. The other uses of such parameters are unchanged. A literal or string parameter is a parameter declared with the value enclosed in double quotes.

\section*{Parameters}
- BNAME

Bus name, previously defined via the . SEtBus command, or can be implicitly declared with MSB:LSB syntax specified. A limitation of the simplified BNAMEMSB: LSB notation is that bus names cannot contain numbers: BUS18:0 will be equivalent to BUS [18:0] but not BUS1[8:0].
- MSB:LSB

Series of bit names, the most significant bit being defined first. This mechanism can be used to implicitly declare . setbus.
- TN

Time in seconds at which the bus signal is equal to val Volts.
- VAL

Bus signal voltage level at time TN .
- \(\mathrm{VHI}=\mathrm{VAL}\)

Upper bus signal voltage level. Default is 5 V .
- vlo=val

Lower bus signal voltage level. Default is 0V.
- trall=val

The time for a falling signal to reach vLo Volts. Default is 2 ns .
- trise=VAL

The time for a rising signal to reach vHi Volts. Default is 2 ns .
- thold=VAL

The hold time for each signal value, measured from the \(50 \%\) point of the transition.
- tDelay=VAl

The delay time before a signal pattern starts.

\section*{- BASE}

Keyword indicating that the bus signal number system is to be defined.
OCT
Keyword indicating that bus signals are defined in octal.
DEC
Keyword indicating that bus signals are defined in decimal. Default.

\section*{BIN}

Keyword indicating that bus signals are defined in binary.

\section*{HEX}

Keyword indicating that bus signals are defined in hexadecimal.
- \(\mathbf{P}\)

Keyword indicating the bus signal is periodic.
- SIGNED=NONE | 1COMP | 2COMP

Defines how negative values inside bus patterns are managed.
noNe-negative values are forbidden (default)
1COMP-the one's complement of the value is done
2COMP-the two's complement of the value is done
Must be specified before the pattern parameter when specified together.
- PATTERN

Keyword indicating the bus signal is pulsating (digital-like). Integer values can be specified, a bus value specifying base=bin pattern 101 has the same effect as specifying base=dec pattern 5. The pattern on a .Sigbus command can also be specified via a parameter using (PAT) where PAT is the parameter as specified in the .PARAM statement. For example:
```

.PARAM PAT=3
.SIGBUS toto VHI=1.8 VLO=0 TFALL=100ps

+ TRISE=100ps THOLD=5ns TDELAY=0 BASE=DEC
+ PATTERN \$(PAT)

```
- \(\quad \$(\mathrm{PAT})\)

PAt is a previously declared parameter in the special case of the pattern specification above.
- z

Releases the applied signal of a bus. When the Z state is active, the signal will be disconnected from the node, and the node will be computed by Eldo as if it were a non-input signal.
- FILE=file

Allows Eldo to read values from the specified file. This is a text file that supplies the timedigital value pairs. The file can have multiple lines and can have any number of point pairs per line. Parentheses are not allowed in this file, and continuation line signs " + " are optional. The format of the input file is the same as that used when specifying an input file for a PWL source, see the "Piece Wise Linear Function" on page 338.

\section*{Examples}
.sigbus can be used to implicitly declare . Setbus, providing that BNAMEMSB:LSB, BNAME [MSB:LSB] or BNAME<MSB:LSB> syntax is used as shown below:
```

.SIGBUS BUS2:0
.SIGBUS SELECT[2:0]
.SIGBUS DOUT<3:0>

```
is equivalent to:
```

.SETBUS BUS BUS2 BUS1 BUSO
.SIGBUS BUS
.SETBUS SELECT SELECT[2] SELECT[1] SELECT[0]
.SIGBUS SELECT
.SETBUS DOUT DOUT<3> DOUT<2> DOUT<1> DOUT<0>
.SIGBUS DOUT

```

A "Z" state can be specified for a single signal of a bus, shown in the example below:
```

.SIGBUS B<1:0> VHI=2 VLO=0 TFALL=1n TRISE=1n THOLD=200n

+ TDELAY=0 BASE=BIN
+ PATTERN OO O1 OZ 00 01

```

The example below shows a .sigbus command with file specification:
```

.SIGBUS A[3:0] VHI=1 VLO=0 THOLD=1 BASE=BIN FILE=bus_input

```

This example uses the following file, bus_input, as input:
```

---------------- bus_input file -----------------------------

# Testing .SIGBUS A[3:0]

0 1111
10e-9 0001
20e-9 0010
30e-9 0100
40e-9 1000

```

The example below shows the sweeping of literal (string) parameters is allowed, but only when used in conjunction with a .SIGbus command. The example declares a bus and assigns it using hexadecimal value HX000. Then the default value is replaced by "HX001", a transient simulation is performed, and the value is replaced by "HX010".
```

.param pat="HXOOO"
.sigbus vplus[9:0]

+ VHI=vdd
+ VLO=0
+ BASE=DEC
+ PATTERN \$(pat)
.step param pat list "HXOO1" "HX010"

```

\section*{.SINUS}

\section*{Sinusoidal Voltage Source}
.SINUS NODE VO VA FR [TD [THETA]]

\section*{Parameters}
- NODE

Node name between which the source is connected to and ground.
- Vo

Offset voltage in volts.
- VA

Sine wave amplitude in volts.
- FR

Frequency in Hertz.
- TD

Delay time in seconds. Optional.
- theta

Damping factor in \(\boldsymbol{s}^{-1}\). Optional.
Note
The generated waveform is described by:
\[
V=V O+V A \times \sin (2 \pi \times F R(t-T D)) \times \exp (-(t-T D) \times T H E T A)
\]

For more information, refer to the Sources chapter.

\section*{Example}
```

.sinus n2 4.0 1.0 1meg 0.0

```

Specifies a sine wave applied between node n 2 and ground with a 4 V offset voltage, 1 V amplitude, 1 MHz frequency and zero delay.

\section*{.SNF}

\section*{Spot Noise Figure}
```

.SNF INPUT=(LIST_OF_DEVICES) OUTPUT=(LIST_OF_DEVICES)

+ [INPUT_TEMP=VAL] [NOISETEMP=VAL]

```

A new number, SNF (Spot Noise Figure), is calculated. When specifying the input_temp=VAl, the noise at the input will be computed at input_temp. When noisetemp is specified in the . SNF command, this is equivalent to specifying the parameter on all sources in the netlist. This option will take priority over the INPUT_TEMP parameter whether it is used on a source or in the . SNF command. Then, the total noise contribution will be calculated by:
\(S N F=\frac{\text { (Input noise at INPUT_TEMP+Other noise sources at TREF - Output noise at TREF) }}{\text { Input noise at INPUT_TEMP }}\)
Note
When noisetemp is specified, it will replace input_temp in the equation above.

If neither inPut_TEMP nor noisetemp are not specified, then the method of calculation will be:
\[
S N F=\frac{(\text { Noise in circuit }- \text { noise due to output })}{\text { Noise due to source }}
\]

Multiple . SNF commands are supported in Eldo and Eldo RF.

\section*{Parameters}
- LIST_OF_DEVICES

This can contain wildcard ' \(\star\) ' characters anywhere in the name. Each item must be separated with a white space or a comma. Brackets are optional. However, if more than one name is provided, then commas and brackets must be used.

\section*{Example}
```

.SNF INPUT=(XM1*.M*,XM[1-3]*) OUTPUT=M19

```

The example above shows how it is possible to use wildcard characters.
.SNF INPUT \(=(\mathrm{XM} 1, \mathrm{XM} 2 *)\) OUTPUT=M19
This number is frequency dependent, hence a curve is generated that can be plotted via .Рцот nOISE SNF in exactly the same way one can plot:
.PLOT NOISE INOISE

\section*{Note}

The . SNF command provides results only if a .NOISE or .SSTNOISE (Eldo RF) command is present.

\section*{.SOLVE}

\section*{Sizing Facility}
```

.SOLVE PARAM param_name MIN MAX expr=expr [TOL=VAL]

+ [RELTOL=VAL] [GRID=VAL]
.SOLVE obj_name [W | ] MIN MAX expr=expr [TOL=VAL]
+ [RELTOL=VAL] [GRID=VAL]
.SOLVE CNAME [W|L] MIN MAX OPSIZE [TOL=VAL]

```

Used in conjunction with a DC analysis only. Eldo sizes the specified component to match given constraints. This command can be used to solve the value of a parameter. The target may be \(\mathbf{V}(\mathrm{NODE})=<\mathrm{VAL}\rangle\), or \(\mathrm{I}(\mathrm{Vxx})=<\mathrm{VAL}>\), or an expression (for example \(\mathrm{V}(\) NODE1 \()+\mathrm{V}(\) NODE2 \()\) ).

\section*{Parameters}
- CNAME

Name of the component to size. Legal names are R, MOS, \(\mathbf{V} \mathbf{x x}\), \(\mathbf{I}_{\mathrm{xx}}\).
- min, MAX

Bounds to search for a solution, expressed in correct units.
- opsize

Request component sizing so that the voltage on a specific node or current through a voltage source matches given constraints. The syntax is as follows:

V ( NODE ) = VAL
Specifies that the component should be sized so that the voltage on the specified node be equal to VAL, with tolerance тоц.
\(I(V x x)=V A L\)
Specifies that the component should be sized so that the current through the specified voltage source be equal to VAL, with tolerance tol.
- \(\mathrm{w}, \mathrm{L}\)

Keywords identifying width or length for MOS transistors. Optional.
- TOL=VAL

Required accuracy, specified in absolute units. Default is the value of the EPS parameter. Optional.
- GRID=VAL

Means the result must be a multiple of VAL. Optional.
- reltol=Val

Adds the relative tolerances. Optional.
There are two points to bear in mind when using the .solve command:
-. solve works in the case where there is a 0 in the interval, and if the function is monotonous in the interval, but cannot be used to find a MIN or a MAX.
- the default absolute tolerance for .solve is EPS; specify another value in the .solve command to reset this default.

\section*{Examples}
```

.solve m1 w 10u 50u v(2)=0.245v tol=1u

```

Specifies that the width of transistor m 1 be sized to make the voltage on node 2 equal to 0.245 V with a tolerance of \(1 \mu \mathrm{~V}\). Maximum and minimum values of the width are \(50 \mu \mathrm{~m}\) and \(10 \mu \mathrm{~m}\) respectively.
\[
\text { .solve m3 } 1.5 \mathrm{u} 3.5 \mathrm{u} \text { i }(\mathrm{v} 2)=0.2 \mathrm{~m} \text { tol }=0.05 \mathrm{~m}
\]

Specifies that the length of transistor m 3 be sized to make the current through voltage source v 2 equal to 0.2 mA , within a tolerance of 0.05 mA . Maximum and minimum values of length are \(3.5 \mu \mathrm{~m}\) and \(1.5 \mu \mathrm{~m}\) respectively.

\section*{.START_TIME}

\section*{Simulation Start Time}
.START_TIME time_value
Forces Eldo to start the simulation at a specified time (time_value) instead of at time 0. DC input signals are evaluated at time time_value, not at time 0 . This command is similar to the .ADMS_START command available in Questa ADMS. It can be useful if you already have stimuli that you want to reuse instead of rewriting it.

\section*{Parameter}
- time_value

Simulation start time. Default is 0 .

\section*{Example}

V1 10 pwl \(0010 n 1015 n 10\)
.start_time 10n
The DCOP value for node 1 will be 10 V , because that is the value at the 10 ns specified simulation start time.

\section*{.STEP}

\section*{Parameter Sweep}
```

.STEP TEMP|DIPOLE INCR_SPEC
.STEP MOS W|L INCR_SPEC
.STEP MNAME PARAM_NAME INCR_SPEC
.STEP PARAM PARAM_NAME INCR_SPEC, {[VALSTART] VALSTOP VALUE}
.STEP ITEM INCR_SPEC {ITEM2 BOUND}
.STEP (ITEM1,ITEM2... ITEMn)

+ LIST | = (VALi1, VALi2... VALin)... (VALj1, VALj2... VALjn)
.STEP (ITEM1,ITEM2... ITEMn) LIST FILE=FILE

```

Used to perform several simulations while sweeping one circuit parameter or several circuit parameters simultaneously (multiple-sweep). Nested sweeps can also be specified. Further nesting levels can be applied by additional .step commands. There is no limit to the depth (levels) of nested sweeps possible.

By default, the second run in . STEP uses the result of the previous STEP as an initial guess. Setting option nomemstr means Eldo will not use the results of the previous STEP run as an initial guess for the next one.

When specifying multiple sweeps, secondary incr_spec's cannot define the number of points. Eldo will determine the number of points from the first incr_spec defined and then set the same number for subsequent increment steps. This makes it possible to set multiple items and have them change concurrently, then subsequent .STEP commands would provide the next level of nesting.

The series of parameters on the right of the equals sign indicate a series of ' \(n\) ' values enclosed in brackets, which must be specified. The number of terms of this series corresponds to the number of simulations, and ' \(n\) ' items would change at each simulation.

To perform a parameter vector sweep, with all parameters taking their values from lists, use the last syntax shown above and ensure that ITEM is correctly specified for parameter items, for example specifying ( \(\mathrm{P}(\mathrm{IG1}\) ), \(\mathrm{P}(\mathrm{LR1})\) ) to sweep parameters IG1 and LR1.

The command has the ability to sweep several parameters at the same time using the . STEP PARAM syntax. Multiple increment step specifications can be made. This is in order to be able to have "windows" with more points than in other regions.

The sweeping of literal parameters (parameters declared with the value enclosed in double quotes) is only allowed when used in conjunction with a .sIgbus command.
.MPRUN can be used to take advantage of multi-processor machines for the . Step command. .alter and .temp have higher priority than .step when used with .mprun. Please see ".MPRUN" on page 729 for further information.

\section*{Parameters}
- TEMP

Keyword indicating that temperature is to be swept.
- Dipole

Name of the Dipole (R, C, L, V, I) component whose value is to be swept.
- mos

Name of the MOS component whose w or \(\mathbf{x}\) parameter is to be swept.
- W, L

Keywords identifying either MOS width or length respectively.
- MNAME

Model name, of which a parameter PARAM_NAME is to be swept.
- PARAM_NAME

Name of the parameter to be swept.
- param

Keyword to identify that a globally declared parameter is to be swept. Multiple increment step specifications can be made. Non-primitive parameters can be specified.
- LISt

Keyword specifying that a list of individual values are to be swept.

\section*{Note}

For multiple increment step specifications: Be careful of the character "," which is used for separating the different windows. If not specified, VALSTART is assumed to be the VALSTOP value of the preceding window.
\(\qquad\)
.TRAN ... SWEEP will not work if PARAM is specified and a warning message will be issued.
- item

Can be one of the following:
```

P(global_var)
E(device,parameter)
M(model_name,parameter)
EM(device_name,model_parameter_name)
LIB([KEY=]libname)
P
Parameter item.

```

E
Element item.
M
Model item.
EM
Model item attached to a specific Element. Affecting the model parameter of this new private model created for device_name, leaves the original model unchanged. Once . STEP is complete, this private model is discarded, and the original model is attached back to the device.

LIB
Library item. A list of strings is expected, of type LIST as specified in INCR_SPEC below. Used to make several Eldo runs, each of them using a different variant of the libraries. The library can be identified using its key instead of using its filename (with full library path). In this case the key keyword is mandatory. If not set, Eldo will consider the argument of the .Step lib as a filename.
- INCR_SPEC

Specifies the increment step of sweep.
Specification of the increment step may be either of the following:
VALSTART VALSTOP [DEC|OCT|LIN|INCR] VALUE
LIST \{VAL1 VAL2 ... VALN\}

\section*{VALSTART}

Initial value of sweep.

\section*{VALSTOP}

Final value of sweep.

\section*{LIN}

Optional keyword, explicitly selecting a linear sweep.

\section*{INCR}

Incrementing value of sweep. This is the default.
DEC
Keyword to select a logarithmic sweep.

\section*{ОСт}

Keyword to select an octave sweep.
LIST
Keyword specifying that a list of individual values are to be swept. Accepts character strings for dealing with the ITEM of type LIb(libname).

\section*{VALUE}

Specifies the number of points per decade and octave for DEC and OCT respectively, the total number of points for LIN, and the value of increment for INCR.

\section*{VAL1. .VALN}

A list of values to be applied to the specified parameter at each point in the sweep.
- BOUND

Same as INCR_SPEC, except that only boundaries are provided. The increment value is chosen according to the number of runs imposed by the first swept parameter.
- FILE=file

Allows Eldo to read values from the specified file. This is a text file that supplies the timecurrent ( tn in) or time-voltage ( tn vn ) pairs. Engineering units (for example 9ns) are allowed. The time-value pairs are separated by spaces, commas or newline characters. The file can have multiple lines and can have any number of point pairs per line. Parentheses are not allowed in this file, and continuation line signs " + " are optional.

\section*{Note}

To use this command with a device that is situated in a subcircuit, use the nested output format.

1 For more details, refer to ".PRINT" on page 830.

Parameters temp or param specified in the . Step command may also appear on the x-axis of a graphical output when performing a DC analysis.

Eldo will select the model to be assigned to MOS devices according to the geometric size of each device, even if these geometric sizes are modified at run-time via . Ster commands. In previous versions, the selection of the model was done just once at the very beginning of the simulation, and was not changed at run time.

\section*{Examples}
.step temp 25352
Specifies that simulator runs should be carried out between the temperatures 25 and 35 degrees in increments of 2 degrees Celsius.

\section*{Note}

The INCR keyword is optional as this is the default.
```

.step mos_1 w 25u 40u 5u

```

Specifies that simulator runs should be carried out with the width of the transistor mos_1 being swept from \(25 \mu \mathrm{~m}\) to \(40 \mu \mathrm{~m}\) in increments of \(5 \mu \mathrm{~m}\).
```

.step qmod rb 8011010

```

Specifies that simulator runs should be carried out with the base resistance parameter of devices with transistor model qmod being swept from \(80 \Omega\) to \(110 \Omega\) in increments of \(10 \Omega\).
```

c1 1 2 20p
...
.step c1 1p 10p 1p

```

Specifies that simulator runs should be carried out with the capacitor c1 being swept from 1 pF to 10 pF in steps of 1 pF .
```

.step x1.r1 0.1k 0.5k 0.1k

```

Specifies that simulator runs should be carried out with the value of the resistor \(\mathbf{r} 1\), instantiated using the subcircuit instance name \(\mathbf{x} 1\). The resistor value should be swept from \(0.1 \mathrm{k} \Omega\) to \(0.5 \mathrm{k} \Omega\) in increments of \(0.1 \mathrm{k} \Omega\).
```

.param rl 1k
.step param r1 1k 2k 1k, 2k 4k 500

```

Specifies that the value of resistor rl will be swept from \(1 \mathrm{k} \Omega\) to \(2 \mathrm{k} \Omega\) with a step of \(1 \mathrm{k} \Omega\), and then from \(2 \mathrm{k} \Omega\) to \(4 \mathrm{k} \Omega\) with a step of \(500 \Omega\).
```

- param $\mathrm{p} 2=100 \mathrm{k}$
- param p1=sqrt (p2)
...
.step param $\mathrm{p} 1 \mathrm{1k} 5 \mathrm{k} 1 \mathrm{k}$

```

This example shows how a non-primitive parameter p1 can be specified.
The following example shows how the command can be used to define a multiple run by a list of parameters:
```

.step param (p1 p2 ...pn) list (val11 val21 ...valn1)

+ ...(valj1...valjn)

```

This will perform j runs:
```

run1: p1=val11, p2=val21 ... pn=valn1
run2: p1=val21 ...
..
runj: p1=valj1, ... pn=valjn

```

The following example declares a bus and assigns it using hexadecimal value HX000. The default value is then replaced by "HX001", a transient simulation is performed, and the value is replaced by "HX010".
```

.param pat="HXOOO"
.sigbus vplus[9:0]

+ VHI=vdd
+ VLO=0
+ BASE=DEC
+ PATTERN \$(pat)
.step param pat list "HX001" "HX010"

```

The following example shows how the command can be used to sweep Models attached to specific Elements:
```

M1 ... NMOS W=...
M2 ... NMOS W=...
.MODEL NMOS NMOS VTO = 1
.STEP EM(M1,VTO) O 5 1

```

For this example, Eldo will:
1. Emulate a command .moddur m1

A new model nmos.m1 is created, which is private to m1.
All parameters of nmos.m1 are initialized to the NMOS values.
2. Five Simulations will be performed, for nmos.m1.vto varying from 0 to 5. nmos.vto remains at 1.0 .
3. nMos.m1 is discarded: model attached to m1 is NMOS again.

Note
As in the .MODDUP case, parameter dependencies are propagated.
. PARAM P1 \(=550\)
M1 ... NMOS \(\mathrm{W}=.\). .
M2 ... NMOS W=...
.MODEL NMOS NMOS VTO=1 UO=P1
.STEP (EM (M1,VT0),P(P1)) \(=(1,550)(2,600)\)
In the example above, for both nmos.m1 and nmos, the uo value will be identical.

The following examples show how the command can be used to sweep Parameters, Elements, Models, or Models attached to specific Elements:
```

.PARAM P1=1u
.MODEL NMOS NMOS LEVEL=1 VTO=2
M1 p1 p2 p3 p4 NMOS w=p1 l=3u
M2 p1 p2 p3 p4 NMOS w=p1 l=3u
...
.end

```

After the above specification, the following four . STEP commands are valid:
.STEP P(P1) 1u 10u 1u
Parameter P1 varies from \(1 \mu\) to \(10 \mu\) in steps of \(1 \mu\).
.STEP E (M1,l) 3u 4u 1u
Length of Element m 1 varies from \(3 \mu \mathrm{~m}\) to \(4 \mu \mathrm{~m}\) in steps of \(1 \mu \mathrm{~m}\).
```

.STEP M(NMOS,VTO) 1 3 1

```

Parameter vto of model nmos varies from 1 to 3 in steps of 1.
```

.STEP EM(M2,VTO) 1 4 1

```

A private model will be assigned to m 2 . vто of model attached to M 2 will vary from 1 to 4 in steps of 1 ; Vто of model attached to m1 will remain unchanged.

The following defines a two-level nested sweep. The first loop is defined by the first . step. The resistor, R22, will be swept from \(20 \mathrm{k} \Omega\) to \(100 \mathrm{k} \Omega\) in a linear \(1 \mathrm{k} \Omega\) increment. This defines 81 points for the first loop.
```

.STEP E(R22,R) 20K 100K LIN 1K M(MOS1,COX) 0.4M 0.3M
.STEP P(GLOBAL_VAR) 1 1000 DEC 10 E(C_CUPL,C) 100p 500p LIN

```

The second item, the MOS model named mosi would have the parameter cox swept from 0.4 M down to 0.3 M in increments that produce 81 points (that is, \(a b s(0.3 M-0.4 M) / 81\) ). The order is important and would need to be preserved. The number of points is defined by the first increment specification so that the entire .step command will have a consistent number of points.

The resistor and cox parameter would increment/decrement together:
```

(20K, 0.4M)
(21K, 0.38977M)
(100K, 0.3M)

```

The second nesting level is defined by the second . step command. The global parameter named GLobal_Var will be swept from 1 to 1000 in decade logarithmic steps, producing 31 increments. The capacitor, c_cupl, would be stepped from 100 pF to 500 pF linearly with 31 steps together with the GLOBAL_VAR parameter.
```

.STEP PARAM (E (R1,R) TEMP LIB(corna.lib)) LIST

+ (20k 27 typ)
+(10k -40 fast)

```

Specifying the above means that two simulations will be performed:
- The first with R1 value of 20k, TEMP is 27 and uses the LIB variant typ for file corna.lib.
- The second with R1 value set to 10 k , a TEMP value of -40 and the LIB variant fast of the file corna.lib.

The following example shows a parameter vector sweep, with all parameters taking their values from lists. Eldo will sweep parameters IG1 and LR1 over four simulations. The first simulation with IG1 at 10u and LR1 at 1000u. The last simulation with IG1 at 100u and LR1 at 100u.
```

.param IG1=10u LR1=1000u
.step (p(IG1),p(LR1)) LIST (10u, 1000u) (20u, 500u) (50u, 200u)

+ (100u, 100u)
i1 1 0 ig1
r1 1 0 '10e6*lr1'
.plot dc v(1)
.dc

```

The following example shows how the . STEP command is used to make several Eldo runs, each of them using a different variant of the libraries, using the keyword LIB (libname):
```

.LIB mylib TYP
.STEP LIB(mylib) TYP MIN MAX
.END

```

Three simulations will be performed: one using the variant TYP of mylib, another one using the variant MIN, and a last one using the variant max.

\section*{Note}

The LIB specification can be used with any other specification.

\section*{Note}

TYP, MIN, and MAX are not keywords, but are the character strings that can appear as the 2nd arguments of the .LIB command (.LIB FNAME [LIBTYPE]). Usually, variant names are TYP, MIN, and MAX, but they can be any string.
```

.STEP P(P1) 1 2 0.5 LIB(mylib) TYP MIN MAX

```

Here, Eldo will perform three simulations:
- one with both \(\mathrm{P} 1=1.0\) and mylib using variant TYP
- one with both \(\mathrm{P} 1=1.5\) and mylib using variant min
- one with both \(\mathrm{P} 1=2.0\) and mylib using variant MAX

\section*{Limitations on Library Variants}
- Subcircuits are not replaced.

When . LIb is specified in the input file, it can be used to select a subcircuit to be included in the design. Taking a subcircuit from another library than the library specified in the input file could result in a change of topology (and changing topology of the current design is strictly impossible), therefore Eldo would issue an error whenever the user attempted to substitute one subcircuit for another one.
- Switching between GUDM and non-GUDM models is prohibited. Similarly, switching between GUDM models is prohibited.
- Only MOS, BJT, DIODE, JFET, R, L, and C .model commands can be substituted. Attempting to substitute other kinds of models will lead to an error.

\section*{.SUBCKT}

\section*{Subcircuit Definition}
```

.SUBCKT NAME NN {NN} [(ANALOG|OSR|DIGITAL)]

+ [(NONOISE)] [(INLINE)] [[PARAM:] PAR=VAL {PAR=VAL}] [STATISTICAL=0|1]
<CIRCUIT_COMPONENTS>
ENDS [NAME]
SUBCKT LIB FNAME SNAME [LIBTYPE]

```

A subcircuit consists of Eldo, FAS and FIDEL elements. The subcircuit is defined in the circuit description file by groups of elements beginning with a . SUBCKт command and terminating with a . ENDS command. All components and nodes used in the subcircuit definition are known only locally, unless they have been globally defined via the .GLOBAL or .PARAM commands. .MODel specifications inside the subcircuit are also known only locally. There is no limit to the size or complexity of the subcircuit.

\section*{Note}

Care must be taken when using the .PARAM command to ensure that no unwanted parameter assignments are made.

Subcircuit definitions may be nested. The inner subcircuit definitions are local to the subcircuit definition in which they are defined, that is, they are not valid outside of it.

Subcircuits may be parameterized. Symbols may be used as values within the subcircuit body which may be assigned values when the subcircuit is instantiated. A subcircuit may be stored in a library file, in which case the second syntax above and the .LIb or .ADDLIB commands should be used. The second syntax allows no continuation lines.

The subcircuit may optionally be simulated using the differentiated accuracy system. The iteration technique used to process the subcircuit is chosen by the (ANALOG) optional keyword. Usually, a circuit with (ANALOG) specified indicates 'high accuracy'.

\section*{Note}

.MACRO is equivalent to . SUBCKT.

By default, when Eldo encounters multiple definitions of . Suвскт statements an error is reported and the simulation is stopped. Specify option usefirstdef to force Eldo to only use the first definition (any further definitions are ignored) to allow the simulation to proceed.

\section*{Parameters}
- NAME

Name of the subcircuit. May also be specified with the . EnDS command if desired.
- NN

Names of the subcircuits nodes. Nodes are referenced in the same order that they are called in the subcircuit call statement. Ground (or 0V) may not be referenced in this list.
- LIB

Keyword indicating a subcircuit library file is to be used.
- FNAME

Name of the library file that contains the subcircuit description.
- SNAME

Name of the subcircuit stored in library file FNAME. See "Library variant management" on page 694 in the . Lib command description for further details.
- (ANALOG)

Keyword used with the differentiated accuracy system indicating that the subcircuit should be solved using Newton block iteration techniques. These techniques are used in conjunction with the EPS parameter in the .OPTION command. (ANALOG) basically means "high accuracy."
(1)

Before using the differentiated accuracy system see the relevant section in the Speed and Accuracy chapter.

\section*{- (OSR|DIGITAL)}

Used to stop propagation of the ANALOG flag across the hierarchy. In addition the flag will request Eldo to use OSR in the selected blocks, if possible (that is, MOS subcircuit with OSR flag could then be solved by OSR, but BJT subcircuit will still be solved by Newton even if flag OSR is set).
- (NONOISE)

Specifies that all subcircuit objects are noiseless. However, the appearance of a flag noise at a lower level of subcircuit hierarchy overrides the effect of a (NONOISE) flag at a higher level. This parameter must be specified before any PARAM: specification, if any.
- (INLINE)

When specified, Eldo will not print the full hierarchical name of the device which has the same name as the . subckт. The effect of this option is for print out in the . op table only. This parameter must be specified before any PARAM: specification, if any.

\section*{- PARAM:}

Keyword indicating parameter allocation within the subcircuit definition. Optional.
- \(\quad \mathrm{PAR}=\mathrm{VAL}\)

Specifies that the parameter PAR is assigned the value VAL inside the subcircuit, unless another value is assigned to the parameter when the subcircuit is instantiated.
i
In case of M factor usage, see also "M53" on page 979. With some descriptions, Eldo will generate the following error message:
ERROR 712:SUBCKT "XXX": cannot define a parameter named 'M'
- STATISTICAL=0|1

Specify whether any statistical variation due to Monte Carlo, worst case, or DC mismatch analysis can be applied to the subcircuit. 0 means the subcircuit components will keep their nominal values. 1 means the subcircuit components have statistical variation applied. The global default can be specified via option statistical. Default is 1 .
- NAME

Name of the subcircuit. May or may not be specified.
- LIBTYPE

Name of a library variant to be used.
1. For details of subcircuit instance syntax refer to "Device Models" on page 119.

\section*{Related options}

USEFIRSTDEF (see "USEFIRSTDEF" on page 962), dSCGLOB, see "DSCGLOB=X|GLOBAL" on page 976

\section*{Examples}
```

.subckt inv n1 n2 n3 n4 param:p1=10u r1=8u
m1 n3 n2 n4 n4 pmos w=p1 l=r1
m2 n3 n2 n1 n1 nmos w=p1 l=r1
.ends inv
...
x1 vss n8 n9 vdd inv p1=5u r1=5u

```

Specifies the subcircuit inv. Nodes declared in the subcircuit are local. The parameters p1 and r1 are assigned values both at instantiation and in the . subckт command.
```

.subckt w1 n1 n2 n3 n4 (analog)

+ param:r1=10u r2=5u
m1 n1 n4 n5 0 nmos w=r1 l=r2
m2 n5 n5 n2 0 nmos w=r1 l=r2
m3 n4 n5 n3 0 nmos w=r1 l=r2
.ends w1
x1 vss 0 0 vdd w1

```

Specifies the subcircuit w1. This subcircuit is defined to be solved only using Newton block iteration techniques due to the presence of the (ANALOG) optional keyword.
```

*SUBCKT definition
.subckt inv n1 n2 n3 n4

```
```

m1 n3 n2 n4 n4 pmos w=w1 l=l1
m2 n3 n2 n1 n1 nmos w=w2 l=l2
.param l1=5u
.ends inv
...
*main circuit
x1 vss n8 n9 vdd inv w1=60u w2=20u
.param 12=5u

```

Specifies the subcircuit inv using variables w1, 11, w2 and 12 . Note the use of the .PARAM command in this example. The value of the parameter 11 has been assigned a value in the subcircuit inv and so is local to this subcircuit, whereas the parameter 12 has been assigned a value on the main circuit level and so any subsequent instances of the parameter 12 in other subcircuits would also be assigned this value.
```

.subckt outer n1 n2 n3 n4
q1 n1 n5 n6 pbip
.subckt inner n1 n2 n3
r1 n1 n3 1k
r2 n3 n8 4k
...
.ends inner
x1 n10 n12 vdd inner
.ends outer
x1 n21 n25 n30 vdd outer

```

Specifies and instantiates a subcircuit inner nested inside another subcircuit outer.

\section*{Order of Precedence of Subcircuit Parameter Assignments}

Parameters used within a subcircuit may be defined in several ways.
- In the subcircuit instantiation:
x1 N1 N2 N3 MY_SUBCIRCUIT P3=10
- Internally, within the subcircuit:
```

.SUBCKT MY_SUBCIRCUIT
.PARAM p3=20
.ENDS

```
- In the subcircuit declaration:
```

.SUBCKT MY_SUBCIRCUIT P1 P2 P3 PARAM: p3=2

```
- Or globally in the top level netlist:
. PARAM p3=5
X1 N1 N2 N3 MY_SUBCIRCUIT
The precedence of these parameter assignment methods is, in descending order, subcircuit instantiation, internal subcircuit, subcircuit declaration which acts as a default only, and finally global declaration.

Use option PARHIER to control the priorities for parameters.
```

    Note
    . PARAM assignments are order dependent within the netlist. Thus, a parameter value
    assigned using the . PARAM command will only apply to subcircuits instantiated after this
    .PARAM command. Therefore, for the below:
    .SUBCKT INV
    .PARAM p1=v0
    .ENDS
    x1 ... inv
    .param \(\mathrm{p} 1=\mathrm{v} 1\)
    This is accepted, and p1 retains the value of v0 within \(\mathbf{x} 1\) (when option Parhier is
    set to local).
    ```

\section*{Accessing Nodes Inside Subcircuit Instances from Outside}

The following example illustrates how inner nodes may be accessed from outside of a subcircuit instance in which they defined.
```

.subckt inner n1 n2 n3
r1 n1 n3 1k
r2 n3 n8 4k
q27 n1 n7 n8 nbip
.ends inner
.subckt outer n1 n2 n3 n4
q1 n1 n5 n6 pbip
x1 n10 n12 vdd inner
...
ends outer
x13 n21 n25 n30 vdd outer
cmill1 x13.n1 x13.n5 1.2p
cmill2 x13.x1.n1 x13.x1.n5 0.9p

```

Where cmill1 is the Miller Capacitance of \(\mathbf{q} 1\) located inside the subcircuit \(\mathbf{x} 13\) and \(\mathbf{c m i l l} 2\) is the Miller Capacitance of q27 located inside \(\mathbf{x} 1\) which in turn is located inside \(\mathbf{x} 13\). Note that in this example, the capacitances are declared from outside of the subcircuit definitions.

\section*{(INLINE) Keyword Example}

The following example illustrates how the (INLINE) keyword can be specified on the . SUBCKT instance, so that Eldo will not print the full hierarchical name of the device which has the same name as the . Subckт.
```

X1 ... MFOO
X2 ... MFOO
.SUBCKT MFOO ... (INLINE)
M1 ...
MFOO
M2
...

```

\section*{. ENDS}

Then, in the OP table, it will not be \(\mathrm{X} 1 . \mathrm{MFOO}\) and \(\mathrm{x} 2 . \mathrm{MFOO}\) which appear, but simply x 1 and X2.
X1.M1, X2.M1, X1.M2 and X2.m2 names will be printed out unaffected.

\section*{DSCGLOB Option Example}

Nodes which appear in subcircuit definitions have priority over the nodes defined with . global statements. Option dscglob can be used to change this behavior. For example:
```

.GLOBAL QWE
VG QWE O DC 3
*.SUBCKT with a global node name in argument list
.SUBCKT B QWE
R1 QWE O 1K
.ENDS
V2 PIN2 0 DC 2
X2 PIN2 B

```

By default, Eldo will connect R1 between PIN2 and 0 because the symbolic subckt pin QWE is related to real node PIN2.

When option dscglob=GLObAL is specified Eldo will connect R1 between global node QWE and 0 .

\section*{.SUBDUP}

\section*{Subcircuit Duplicate Parameters}
. SUBDUP SUBCKT_INST_NAME
This command is used to inform Eldo of the duplicate parameters and models which are local to the subcircuit. Also, it allows access to parameters in the hierarchical form for SimPilot. This command is useful when Eldo is running in conjunction with SimPilot.

\section*{Example}
```

.subckt xa 1 2
.param p1 = 2
.param p3 = p1*p2
r1 1 2 p3
.ends xa
i1 1 0 1
x1 1 0 xa p2 = 1
i2 2 0 1
x2 2 0 xa p2 = 1
.dc
*.step param xa.p1 5 6 1 ! step p1 in both instance X1 and X2
.subdup x1
.step param x1.p1 5 6 1 ! step p1 only in instance X1

```

In the above, the first .step command, which is commented out, would step the parameter p1 of both instance X1 and X2, as defined in the common subcircuit XA. This is not as required. In order to change the parameter p 1 only in X1, first a . Subdup command has to be specified, so that x 1 will have a private copy of parameter p 1 , which can then be swept. The final . STEP command will step parameter p 1 only in instance X 1 .

\section*{.TABLE}

\section*{Value Tables}
.TABLE NAME (X1 Y1) \{(XN YN) \}
This command defines tables of run time values to be used in AC, DC or Transient analyses. Values from the table may then be accessed from arithmetic expressions using the function call TABLE (NAME).

\section*{Parameters}
- NAME

Name of the table being defined.
- Xxx Yxx

Data value pairs, whose units depend on the analysis type.

\section*{Note}
\(\qquad\)
The analysis specification (AC, DC, TRAN) is deprecated. It will not print an error if specified but it is not used by Eldo.

\section*{Example}
```

.table ac_table_ex ac (1 1) (10k 10)
.defwave wave1=vdb(s)-table(ac_table_ex)

```

Here, ac_table_ex contains the AC analysis values 1 at 1 Hz and 10 at 10 kHz .

\section*{.TCL_WAVE}

\section*{Waveform Definition Using a Tcl Function}
```

.TCL_WAVE [ANALYSIS] WAVE_NAME=TCL_FUNCTION_CALL

```

Used to define a new waveform using a Tcl function. It is similar to the .DEFwAve command with restrictions applied on the waveform expression, which must be a single Tcl function. The resulting waveform can be used as a normal .DEFWAVE with syntax W (WAVE_NAME).

This allows you to dynamically manage User Defined Functions (UDF) written in Tcl language. The functions of the post-processor library and other commands are available through the Tcl interface.

For loading a Tcl file containing functions into the Eldo Tcl interpreter, see the command ".USE_TCL" on page 929.
For performing a single call to a Tcl function, see the command ".CALL_TCL" on page 559.
For further information on Tcl commands, see the Post-Processing Library chapter of this manual.

\section*{Parameters}
- ANALYSIS

Type of analysis to be used.
- WAVE_NAME

New waveform name.
- TCL_FUNCTION_CALL

The Tcl function. A function can take any kind of arguments: waves, numbers and keywords. These keywords are: IRUN, ICARLO, IALTER which respectively represent the index of the current step, Monte Carlo run, and .alter. NBRUN, NBCARLO, NBALTER which represent the number of steps, Monte Carlo runs, and .ALTER.

\section*{Example}
```

.extract tran label=minin min(v(in),10n,260n)
.extract tran label=maxin max(v(in),10n,260n)
.tcl_wave tran FREQCKIN = FREQM(v(in), meas(maxin), meas(minin))
.defwave tran CKOUTREF='W(FREQCKIN)/8'
.plot tran V(in) W(FREQCKIN) W(CKOUTREF)

```

\section*{.TEMP}

\section*{Set Circuit Temperature}
```

.TEMP TS {TS}

```

The .TEMP command may be used to execute several successive simulations at various temperatures. The .TEMP command works for all analysis types. All input data for Eldo is assumed to have been measured at \(27^{\circ} \mathrm{C}\). Eldo also assumes a nominal temperature of \(27^{\circ} \mathrm{C}\) unless a TNOM statement is present in the .OPTION command.

Note
Any model temperature defined by the тMOD parameter has priority over the .TEMP command, and furthermore, the \(\boldsymbol{T}\) parameter has priority over both TMOD and .TEMP, that is, \(\boldsymbol{T}\) has the highest priority.
.MPRUN can be used to take advantage of multi-processor machines for the .TEMP command. .alter has a higher priority than .temp when used with .mprun. Please see ".MPRUN" on page 729 for further information.

\section*{Parameters}
- TS

The temperature(s) for circuit simulation.

\section*{Example}

Specifies circuit analyses at 0,27 and \(60^{\circ} \mathrm{C}\).

\section*{.TF}

\section*{Transfer Function}
```

.TF OV IN

```

The . Tr command causes the small signal Transfer Function to be calculated by linearizing around a bias point. The gain from in to ov is output along with the input and output impedances.

\section*{Parameters}
- IN

Input voltage source name. Must be an independent source.
- ov

Requests the output voltage of a specific node or current through a voltage source. The syntax is as follows:

V(N1[, N2])
Specifies the voltage difference between nodes N1 and N2. If N2 and the preceding comma are omitted, ground is assumed.

I(Vxx[, Vyy])
Specifies the current difference between the voltage sources \(\mathbf{v}_{\mathrm{xx}}\) and \(\mathbf{v}_{\mathrm{y}} \mathrm{y}\). If \(\mathrm{v}_{\mathrm{y}}\) and the comma are omitted, the current through \(\mathrm{V} \times x\) is output.

Example
```

* voltage source definition
vin 1 0 5
.tf v(3) vin

```

Specifies that the small signal Transfer Function be calculated for the voltage at node 3 with respect to the independent voltage source vin.

\section*{.TITLE}

\section*{Set Title of Binary Output File}
.TITLE name
The first line of the .cir file provides the title of the binary output file (.wdb). However, under a graphical environment the user is not supposed to manually modify the netlist, so this command can be used to define the title of the binary output file.
.title also affects the different banners that appear in the ASCII output file.

\section*{.TOPCELL}

\section*{Select the TOP Cell Subcircuit}
```

.TOPCELL [=] <SUBCKT_NAME>

```

Usually, an automatic extraction tool is used to generate a hierarchical Spice netlist. However, in order to simulate the design, it may be necessary to add an X instance of the TOPCELL subcircuit, and re-specify all interface nodes. In these cases it is easier to use .TOPCELL SUBCKt_NAME, when the associated .subckt subckt_name and the .ends command will be ignored by the Eldo parser.

\section*{Note}

The command . TOPCEll must be specified before any . subckt command.

\section*{.TRAN}

\section*{Transient Analysis}

\section*{Point-Driven Analysis}
```

.TRAN TPRINT TSTOP [TSTART [HMAX]] [SWEEP DATA=dataname] [UIC] [MONTE=val]
.TRAN TPRINT TSTOP [TSTART [HMAX]] [SWEEP parameter_name

+ TYPE nb start stop] [UIC] [MONTE=val]
.TRAN TPRINT TSTOP [TSTART [HMAX]] [SWEEP parameter_name start stop incr]
+ [UIC] [MONTE=val]

```

\section*{Parameterized Analysis}
```

.TRAN INCRn Tn [{INCRn Tn}] [TSTART=val] [SWEEP DATA=dataname]

+ [UIC] [MONTE=val]
.TRAN INCRn Tn [{INCRn Tn}] [TSTART=val] [SWEEP parameter_name
+ TYPE nb start stop] [UIC] [MONTE=val]
.TRAN INCRn Tn [{INCRn Tn}] [TSTART=val] [SWEEP parameter_name
+ start stop incr] [UIC] [MONTE=val]

```

\section*{Data-Driven Analysis}
```

.TRAN DATA=dataname [SWEEP DATA=dataname] [UIC] [MONTE=val]
.TRAN DATA=dataname [SWEEP parameter_name TYPE nb start stop]

+ [UIC] [MONTE=val]
.TRAN DATA=dataname [SWEEP parameter_name start stop incr]
+ [UIC] [MONTE=val]

```

This command activates a transient analysis. Transient output variables (that is, those variables contained within .PRINT and .PLOT commands in the input description file) are calculated as a function of time over a user specified time interval. The initial conditions are automatically determined by a DC analysis (unless the UIC parameter is specified) with all sources that are not time dependent being set to their DC values.

The Integral Equation Method (IEM) is used in .TRAN to solve FNS functions. The algorithm is just used for FNS, and not for the rest of the circuit. . Option nofnsiem reverts to the previous implementation based on state variables.

Multi-threading can be activated for a single DC or TRAN simulation, Eldo will share computer resources on a multi-processor machine. Alternatives are:
- command line flag -mthread (see "-mthread" on page 50) at Eldo invocation, or option mthread in the netlist. Eldo will make use of all the possible CPUs on the machine.
- command line flag -usethread \# (see "-usethread val" on page 56) at Eldo invocation, or option USETHREAD=val. This forces Eldo to use at maximum the specified (\#) number of CPU. The number specified can exceed the number of CPUs available, but this is not recommended, even though Unix will allow it.

Statistics, generated at the end of simulation, show how many CPUs have been used for the current simulation. This number will also be printed out at the beginning of the TRAN simulation.

\section*{Parameters}
- TPRINT

The time interval used for the printing or plotting in the ASCII output .chi file of the results of transient analysis (in seconds). Also used to compute a default hmAx value in case the circuit does not contain any signals (no PWL/SIN, and so on), which is often the case in oscillator circuits. TPRINT can be specified as a parameter or as an expression.
- tStop

The transient analysis duration in seconds. This can be specified as a parameter or as an expression.
- tstart

Start time for printing or plotting. No outputs are stored from 0 to TSTART seconds. This can be specified as a parameter or as an expression.
- HMAX

Sets the maximal internal timestep. When hmax is specified both in the .OPtion command and in the .TRAN command, the hmax in . Option is considered by Eldo. See . OPtIon "HMAX=VAL" on page 965.
- DATA=dataname

Used in conjunction with the .DATA command. The dataname parameter should be specified using the .DATA command. Please refer to ".DATA" on page 585 for more information.
- UIC

Use initial conditions. Eldo does not solve the quiescent operating point before beginning the transient analysis. Eldo automatically initializes all the node voltages itself as well as any user defined initial node voltages included in a . IC command. The uIc option is recommended for the simulation of astable or very large digital circuits.
- \(\mathbf{M O N T E}=\mathrm{val}\)

Monte Carlo analysis. Equivalent to .mc val. The syntax allows a different monte value for each run. However, the actual implementation in Eldo does not account for that: it is the last monte value to be specified in the netlist which will be taken into account.

\section*{-compat flag}

When Eldo is run with the -compat flag, if the .TRAN command has four parameters, for example:
```

.TRAN tprint tstop tstart hmax

```
- if value4 (hmax) < value2 (tstop), it is treated as in Eldo standard mode:
```

.TRAN tprint tstop tstart hmax

```
- if value 4 (hmax) \(\geq\) value2 (tstop), it is treated as a list of INCRn Tn values:
```

.TRAN INCR1 T1 [{INCRn Tn}] [TSTART=val] [UIC]

```
- INCR1, ...n

Used in the .PRINT/.РLOT command for printout purposes only. Between 0 and t1, a value will be printed for each INCR, and so on.
- Tn

Simulation end time.

\section*{Sweep Parameters}

This section contains SWEEP related parameters that are previously unspecified in the Parameters section.
- SWEEP

Specifies that a sweep should be performed on a parameter or device name.
Note
. TRAN ... SWEEP will not work if . STEP PARAM is specified and a warning message will be issued stating that these two ways for specifying a sweep are not compatible.
- parameter_name

Name of the parameter or device name to be swept.
- type

Can be one of the following:
DEC
Keyword to select logarithmic variation.
оСт
Keyword to select octave variation.
LIN
Keyword to select linear variation.

\section*{POI}

Keyword to select a list of frequency points. POI is the same as LIST except that POI expects the number of points nb to be specified as it's first argument.

INCR
Increment of the parameter or device name to sweep. When INCR is specified as the TYPE parameter, the value which directly follows (nb) is the incrementing value.
- nb

Number of points required, for example:
.TRAN 1 n 10 n SWEEP P1 POI 31 k 10 k 100 k
- start

Start value of the parameter or device.
- stop

Stop value of the parameter or device.
- incr

Increment of the parameter or device name to sweep.

\section*{Note}

When INCR is specified as the TYPE parameter, the value which directly follows (nb) is the incrementing value. If INCR is not specified, the incrementing value (incr) must be placed after the start and stop values.

For a circuit not containing any signals (no PWL/SIN, and so on), which is often the case in oscillator circuits, the value of TPRINT is also used to compute a default HMAX value. In such circuits, unless a . OPtion hmax command was supplied, or a very low eps value was given, Eldo would sometimes not detect the transitions that trigger oscillations, or the transitions that would cause them to die out, and designers who are familiar with Spice-like simulators would not understand the reason for Eldo not behaving in a Spice-like way. The reason for such a difference is only because Spice-like simulators use tPrint as a hmax value, while in Eldo, this was not the case.

The scenario inside Eldo is now the following: if the circuit does not contain any stimuli, then the hmax value is either tPRInt, or tStop/denom, whichever value is larger. DENOM is based on eps; denom is 50 by default, and 100 for eps < 100 U .

\section*{Examples}
.tran . 2 u 40 u sweep r 1 INCR 51005 k
.tran . 2u 40u sweep r 1005 k 5
The two lines above are equivalent. Either can be used to specify a transient analysis from 0 to 40us with print time intervals of 0.2 us . The sweep specification forces Eldo to carry out a transient analysis on each value of \(r 1\) starting at \(100 \Omega\) and stopping at \(5 \mathrm{k} \Omega\) with an incrementing value of \(5 \Omega\).
```

.tran 1ns 100ns
.plot tran v(2)

```

Specifies a transient analysis from 0 to 100 ns with a print step of 1 ns . The results of the transient analysis are plotted for the voltage at node 2 of the circuit within the limits specified in the .TRAN command.
```

.tran 2ns 100ns 50ns uic
-plot tran v(4)

```

Specifies a transient analysis from 0 to 100 ns and a print-out from 50 to 100 ns with a print step of 2 ns . The UIC option is also specified indicating that a DC analysis will not be performed and that initial voltage will be set up automatically. The results of the transient analysis are plotted for the voltage at node 4 of the circuit within the limits specified in the .TRAN command.
1. Examples of this type of analysis can be found in "Tutorials" on page 1341.

Parameters are allowed in transient analysis commands as shown in the following example:
```

.param p1 = 1e9
.tran dec 10 1 p1

```
i
NOISE analysis may also be run from within a .TRAN command, see "AC in the middle of a .TRAN" on page 543 for more details.

\section*{.TSAVE}

\section*{Save Simulation Run at Multiple Time Points}
.TSAVE [REPLACE|NOREPLACE] TIME=VALUE [FILE="fileBasename"]
The .tsave command will save the state of the simulation at a specified time point. The state of the simulation is saved to a .iic file. The file can be used to restart the simulation from the specified time point using the . Restart command. See ".RESTART" on page 854. The state of the simulation can be saved at more than one time point by specifying the .TSAVE command for each time point.

For saving a simulation run without specific multiple time points, see ".SAVE" on page 857.

\section*{Parameters}
- REPLACE

All previously saved checkpoint files in the output directory will be removed and replaced with the checkpoint file specified. Default. Optional.
- NOREPLACE

Only the checkpoint file with the same name will be modified, all the remaining checkpoint files will remain unchanged. The checkpoint file will be saved in the output directory. Optional.
- TIME=VALUE

Specifies the time at which the simulation will be saved. Mandatory.
- FILE="fileBasename"

Specifies the first part of the checkpoint file name. The file name will take the form fileBasename_timepoint.iic, where timepoint is the time that the simulation was saved. The file will contain the information from the simulation run for the specified time point. If omitted Eldo will save the file with the name of the top-netlist: if the top-netlist is called spice-on-top.cir Eldo will use the name spice-on-top_.... Optional.

\section*{Examples}
.TSAVE TIME=200ns FILE="spice_ontop"
The state of the simulation will be saved at 200 ns . All previously saved checkpoint files in the output directory will be removed and replaced with the checkpoint file spice_ontop_2.000000E-7.iic.
.TSAVE NOREPLACE TIME=200ns FILE="spice_ontop"
The state of the simulation will be saved at 200 ns . All previously saved checkpoint files in the output directory will remain unchanged if the filename is unique. The checkpoint file will be saved with the name spice_ontop_2.0000000E-7.iic.
```

.PARAM sim=250ns
.PARAM chkpnt_file='"timepoint"'

```
```

.TSAVE noreplace time=sim file=\$(chkpnt_file)

```

The state of the simulation will be saved at 250 ns as defined on the parameter sim. The checkpoint file name will be timepoint as defined by the string parameter chkpnt_file.
\[
\begin{aligned}
& \text {.TSAVE NOREPLACE TIME=10ns FILE="spice_ontop" } \\
& \text { •TSAVE NOREPLACE TIME=100ns FILE="spice_ontop" } \\
& \text {.TSAVE NOREPLACE TIME=1000ns FILE="spice_ontop" }
\end{aligned}
\]

The state of the simulation will be saved at \(10 \mathrm{~ns}, 100 \mathrm{~ns}\) and 1000 ns to three independent files. If noreplace was not specified on the last .TSAVE command the checkpoint files saved at 10ns and 100 ns would be removed.

\section*{.TVINCLUDE}

\section*{Test Vector Files}
.TVINCLUDE [FILE=]FILENAME [COMP=ON|OFF] [ERRNODE[=YES|NO]]
Test vectors can be included in a netlist. This file allows the user to define a bus, specify inputs and check output values. It is possible to compare simulation results using test vectors. A test vector is an external file containing a record of circuit stimulus and response.

\section*{Parameters}
- FILE=

Specifies the filename. Optional.
- filename

Test Vector filename.
- COMP=ON \(\mid\) OFF

Define whether the output vector is compared to simulation results. Default is on. Optional.
- ERRNODE[=YES|NO]

If set to YES (default value), an error is printed for signals using undeclared nodes. If set to no, the following warning is displayed:

Warning 445: COMMAND . TVINCLUDE: node \%s not found (\%s). Test vector specifications ignored for this node.

Boundaries are set by using the following options:
.OPTION LOWVOLTAGE=VAL HIGHVOLTAGE=VAL LOWVTH=VTH1 HIGHVTH=VTH2
- lowvoltage and highvoltage are used for input signals
- lowvth and highvth are used for output checking
- Default values are: lowvoltage=0, highvoltage=5, LOWvth=2.4, highvth=2.6

Note
For more details regarding the setting of boundaries with these options, please refer to "HIGHVOLTAGE=VAL" on page 977.

\section*{Test Vector File Format}

Figure 10-6 shows the contents of a test vector file for a two-input AND gate.
Figure 10-6. Example Test Vector File


A test vector file consists of the following parts:
- Header

The header specifies the units of time used in the test vectors and the direction and order of the inputs and outputs. Refer to "Header" on page 920.
- Comments in Test Vector Files

Comments can appear anywhere in the file. Refer to "Comments in Test Vector Files" on page 921.
- Radix

Test vectors can have a radix value of \(1,2,3\) or 4 . By default the value is 1 .
- Test Vectors

Test vectors consist of a time stamp followed by the input and output signal data at the time indicated by the time stamp. Refer to "Test Vectors" on page 921.

\section*{Note}

There is no provision for line continuation in test vector files. Test vector file line lengths are not limited.

\section*{Header}

The keyword CODEFILE marks the beginning of the header; the keywords CODING(ROM) mark the end of the header. Within the header are three classes of statements:
- UNITS Statement

Specifies the units used for time stamps (the time units of measure) in the test vectors. Format the UNITS statement as follows:
```

UNITS units

```
units
Must be fs (femtoseconds), ps (picoseconds), ns (nanoseconds), us (microseconds), or ms (milliseconds). This optional parameter defaults to fs. Units are case insensitive.
- RISE_TIME and FALL_TIME Statements

Specifies the rise and fall times for digital signals. The optional RISE_TIME and FALL_TIME statements are single-parameter declarations of the digital signal transition durations. If you omit the RISE_TIME and FALL_TIME statements, Eldo uses the DefaultRiseTime and DefaultFallTime simulation option values (default 1e-10). Format the statements as follows:
```

RISE_TIME n
FALL_TIME n

```
n
Specifies a digital transition rise or fall time. The UNITS statement specifies the units of time (fs, ps, ns, or us).
The RISE_TIME and FALL_TIME definitions affect the timing of signals moving from one state to another. Refer to "Timing of Changing States" on page 922.
- INPUTS and OUTPUTS Statements

Defines the direction and order of the signals in the test vectors. The INPUTS and OUTPUTS statements can be declared on single or multiple lines. Signals in the input and output lists can have one parameter denoting a time offset. A signal specification has the following general form:
```

INPUTS signal [(to=n])]...;
OUTPUTS signal [(to=n])]...;
signal

```

A Spice netlist signal name. Specify bidirectional signals in both INPUTS and OUTPUTS statements.
\(\mathrm{to}=\mathrm{n}\)
Specifies a time offset (to) that applies to both inputs and outputs. This parameter causes input forcing or output comparison to be delayed by \(\boldsymbol{n}\) time units (fs, ps, ns, \(\mu \mathrm{s}\), or ms ). The UNITS Statement specifies the units of time.
The time offset is relative to the time the vector is applied. For output signals, if \(\boldsymbol{n}\) is replaced by the keyword max, then the comparison occurs one femtosecond before Eldo reads the next vector.
If no time offsets are specified, inputs start being forced at the vector time.
; (semicolon)
Terminates the INPUTS or OUTPUTS.
In the test vector file example illustrated in Figure 10-6 on page 919, all the inputs are forced at the same time, with no offsets. Output comparisons are delayed until just before the next vector is forced.

\section*{Comments in Test Vector Files}

Comments can appear anywhere in a test vector file. They can take the form of C-style comments (delimited by \(/ *\) and \(* /\) ) or shell-style comments (prefixed by a \# character). Comments that appear within the header are ignored when the test vector file is read.

\section*{Radix}

Test vectors can have a radix value of \(1,2,3\) or 4 . By default the value is 1 . Table \(10-32\) lists the different radix values and their meanings:

\section*{Table 10-32. Test Vector Radix Values}
\begin{tabular}{|l|l|}
\hline Value & Radix \\
\hline 1 & Binary \\
\hline 2 & Decimal \\
\hline 3 & Octal \\
\hline 4 & Hexadecimal \\
\hline
\end{tabular}

\section*{Test Vectors}

The vector portion of the test vector file starts after the header and ends with the keyword END. Format test vectors according to the following form:
```

@timestamp <input_data >output_data ;

```
timestamp
Specifies the simulation time in at which the vector was generated. Supply an integer value (with no decimal). The UNITS Statement specifies the units of time. Eldo applies the vector at this time during verification.
input_data
Specifies the states of the inputs at the simulation time shown by the timestamp. The less than symbol ' <' precedes the input portion of the vector. Refer to Table 10-33 on page 922 for valid state characters.
```

output_data

```

Specifies the states of the outputs at the simulation time shown by the timestamp. The greater than symbol ' \(>\) ' precedes the output portion of the vector. Refer to
Table 10-33 on page 922 for valid state characters.
; (semicolon)
Terminates the vector.
The input and output portions of the vector contain columns of state characters. Each column is associated with one signal, in the order defined in the input and output lists in the header. If a signal is bidirectional, it could have one column in the input portion of the vector and one column in the output portion of the vector.

Table 10-33 lists the different state characters and their meanings:
Table 10-33. Test Vector State Characters
\begin{tabular}{|l|l|l|}
\hline State \(*\) & Meaning for Inputs & Meaning for Outputs \\
\hline \(\mathbf{0}\) or \(\mathbf{L}\) & Force LOW & Verify LOW \\
\hline \(\mathbf{1}\) or \(\mathbf{H}\) & Force HIGH & Verify HIGH \\
\hline \(\mathbf{X}\) & Ignore; do not force & Do not verify \\
\hline. or \(\mathbf{Z}\) & Do not force & Do not verify \\
\hline
\end{tabular}
* Logic level states (L, H, X, and Z) are case insensitive in Eldo.

\section*{Timing of Changing States}

Eldo imposes the following timing rules while changing signal states specified by test vectors:
- Forced state to forced state

A signal changing from a forced state (non-Z) to another forced state begins its transition RISE_TIME (or FALL_TIME) before the vector time so that the signal reaches the new value at the vector time.
- High impedance to forced state

A signal changing from high impedance state \((Z)\) to a forced state starts to be forced RISE_TIME (or FALL_TIME) before the vector time.
- Forced state to high impedance

A signal changing from a forced state to a high impedance state \((Z)\) is tri-stated (released) at the vector time.
- Eldo uses the greater value of the RISE_TIME and FALL_TIME definitions in determining output evaluation timing (refer to Figure 10-7). The input signals always arrive at the evaluation time. However, if the RISE_TIME and FALL_TIME values are different, one evaluation will be performed some time before the transition begins.

Figure 10-7. Test Vector Output Evaluation
Test vector time A

Input Signal


\section*{Note}


Because Eldo determines the test vector output evaluation based on the maximum value of RISE_TIME and FALL_TIME, caution should be exercised when assigning them different values.

The following output evaluations occur:
- The minimum time step ( 1 fs ) before the next transition begins if the next transition is determined by the greater value of RISE_TIME and FALL_TIME.
- Before the next transition begins by the difference between RISE_TIME and

FALL_TIME if the next transition is determined by the lesser value of RISE_TIME and FALL_TIME.

\section*{.UNPROTECT}

\section*{Netlist Protection}
.UNPROTECT
This command is used in conjunction with ".PROTECT" on page 850 to exclude a section of a netlist from being copied into the output file. Can be specified to control the end of the encryption process with the Eldo Encryption tool.

\section*{Example}
```

.PROTECT
vin 2 0 ac 0.5
r1 2 3 5k
c3 3 0 0.1p
.ac dec 10 10e+4 10e+8
.plot ac vdb(3)
.UNPROTECT

```

The lines in a netlist between the two commands . РROtect and . unprotect are not printed to the output file.

\section*{.USE}

\section*{Use Previously Simulated Results}
```

.USE FILE_NAME [NODESET|IC|GUESS|OVERWRITE_INPUT]

```

This command takes a set of voltages previously saved using the . SAVE <fname> DC command, and inserts these as .nodeset, .guess or . Ic values at the point of the circuit where this command is present. It is also possible to have multiple occurrences of the . USE command in an input netlist. See ".SAVE" on page 857.

i
For more details, refer to the section ".SAVE, .USE \& .RESTART" on page 1080 in the Speed and Accuracy chapter.

This command cannot be used with previously saved simulation results from a .TSAVE command.

\section*{Note}

Care must be taken when using a .sav file generated in a previous release as this can cause incorrect simulation results. It is recommended that only .sav files generated with the current release are used.

\section*{Parameters}
- FILE_NAME

Filename into which the DC values were saved via the . SAVE <fname> DC command.
- nodeset

Indicates that the read in voltages should be used as .nOdeset values.
- IC

Indicates that the read in voltages should be used as . Ic values.
- GUESS

Indicates that the read in voltages should be used as .guess values.
- OVERWRITE_INPUT

Has the same effect as guess, however Eldo is allowed to change the DC values of input if they don't match the .ic file. This parameter allows the user to perform AC analysis close to a previous transient saved point (saving with the .SAVE end or . SAVE time command).

\section*{Note}

If . USE OVERWRITE_INPUT is used in conjunction with .AC UIC, then the file referred to in the . USE statement will be used for each AC analysis, and not only for the first one as was the case in versions prior to v6.3. For example, if there is a .step command, then the use file will be used for each AC analysis triggered by the . STEP, and not only by the first one.

\section*{Examples}
```

.use test1.exa nodeset

```

Specifies that DC values found in the file <testl>.exa should be read and used as .nodeset values.
```

.use circuit1.iic ic

```

Specifies that DC values found in the file <circuitl>.iic should be read and used as . Ic values.

\section*{.USEKEY}

\section*{Use Reliability Model Key (Password)}
.USEKEY [MODEL=model_name] KEY=key_value
This reliability analysis command provides the encryption key (password) to be used to allow the UDRM API to retrieve encrypted model parameter's value.

For the complete description of this command and information on all reliability commands, see the separate chapter Reliability Simulation.

\section*{.USE_TCL}

\section*{Use Tcl File}
```

.USE_TCL FILENAME [MODE=PPL|EZWAVE]

```

This command loads the Tcl file filename into the Eldo Tcl interpreter.
This allows you to dynamically manage User Defined Functions (UDF) written in Tcl language. The functions of the post-processing library (PPL), EZwave user-defined functions, and other commands are available through the Tcl interface.

Although the PPL and EZwave contain equivalent functions, the syntax to call the functions is different, and sometimes the function name and parameters are different. It is possible to write user-defined functions that can be used in both Eldo and EZwave.

After loading the Tcl file, Eldo can use all the functions written in this file as if they were macros. This means that these functions can accept any argument, are defined for the whole netlist, and can return both numbers and/or waves.

\section*{i)}

For performing a single call to a Tcl function, see the command ".CALL_TCL" on page 559. For further information on both commands, see the Post-Processing Library chapter of this manual.

\section*{Parameters}
- FILENAME

Filename of the Tcl file to be loaded.
- MODE=PPL|EZWAVE

Select the mode for evaluating Tcl functions. Ppl selects the post-processing library (PPL) functions. EZWAVE selects the EZwave user-defined functions. Default is PPL. Although the PPL and EZwave contain equivalent functions, the syntax to call the functions is different, and sometimes the function name and parameters are different.

\section*{Example}

If resi.tcl contains:
```

proc PARAM_EVAL { a } {
return [expr \$a * 3]
}

```
and the netlist contains:
```

* comment
.use_tcl resi.tcl
v1 1 0 pwl(0 0 10n 10)
r1 1 0 r=PARAM_EVAL(2)
.tran 1n 10n

```
\[
\begin{aligned}
& \text {.plot tran i(r1) } \\
& \text {.end }
\end{aligned}
\]

This example demonstrates how to use a very simple Tcl function in a SPICE-like netlist. . USE_tCl loads the file into an internal Tcl interpreter, making all functions known to Eldo. Thus resistor \(r 1\) gets its value from the Tcl function PARAM_eVAL just as if PARAM_eVAL is a macro (defined with . DEFMAC).

\section*{.USE_VERILOGA}

\section*{Load Compiled Verilog-A Modules}
.USE_VERILOGA filename
Loads compiled Verilog-A modules in Eldo.
The .use_veriloga command finds the specified Verilog-A compiled file and treats its behavior as a part of the Eldo netlist. If the specified Verilog-A compiled file does not exist then Eldo generates an error message.

Refer to the Eldo Verilog-A User's Manual for further information.

\section*{Parameters}
- filename

Name of the Verilog-A source file to be used by Eldo in a simulation.

\section*{.VEC}

\section*{Test Vector Files}
.vec 'file_name'

\section*{Description}

Loads the vector file, file_name, of HSPICE format. For this format of file, see Digital I/O Files in the ADiT User's and Reference Manual.

See also .TVINCLUDE.

\section*{.VERILOG}

\section*{Compile and Load Verilog-A Modules}
.VERILOG filename
Compiles and loads Verilog-A modules in Eldo.
To incorporate Verilog-A modules (contained in a Verilog-A source file) in an Eldo netlist, specify the source file name in a .verilog statement in the netlist.

By default the Verilog-A source file is compiled using the default Verilog-AMS compiler in Questa ADMS.

Refer to the Eldo Verilog-A User's Manual for further information.

\section*{Parameters}
- filename

Name of the Verilog-A source file to be compiled. filename may include a relative or absolute pathname.

\section*{.WCASE}

\section*{Worst Case Analysis}
. WCASE DC \(\mid\) AC \(\mid\) TRAN [OUTPUT=MIN \(\mid\) MAX \(\mid\) BOTH] [VARY=LOT \(\mid\) DEV \(\mid\) BOTH]
+ [TOL=VAL] [ALL] [SORT_REL=VAL] [SORT_ABS=VAL] [SORT_NBMAX=VAL]
Worst Case Analysis computes worst case values for waveform data extracted using the .EXTRACT command according to a set of parameters that have LOT and Dev variations.

For DC sensitivity analysis, the . SENS command can be used, see ".SENS" on page 863. For AC sensitivity analysis, the . SENSAC command can be used, see ".SENSAC" on page 865 .

Worst Case Analysis uses the same цот and/or dev parameters as MC analysis to set these parameters to be varied.

\section*{Note}


Multiple sensitivity and statistical analyses cannot be used simultaneously. Specifically, .DCMISMATCH, .MC, and . WCASE are exclusive. Only one of them can be specified in a netlist.

The keyword, statistical \(=0 \mid 1\), can be specified on X instances, device declarations, or on . subckт definitions, to specify whether any statistical variation due to worst case analysis can be applied to the specified entities. If statistical is 0 , the selected devices will keep their nominal values. If statistical is 1 , the selected devices have statistical variation applied. The global default can be specified via option statistical \(=0 \mid 1\). Default is 1 .

Different entities are able to share the same distribution. Anywhere Eldo accepts LOt/DEv specifications, you can specify LOTGROUP=group_name. Please refer to ".LOTGROUP" on page 701.

Considering a design which contains \(P\) parameters that have a statistical variation, and \(T\) targets (.extract commands), Eldo will perform several simulations:
1. The first simulation is the nominal simulation, using nominal values for the \(P\) parameters.
2. Next P simulations are sensitivity analysis runs, where Eldo applies a small variation to one of the \(P\) parameters, keeping all other parameters to their nominal value, and computes the sensitivity of the T targets relative to the current parameter.

For each of the T targets, Eldo outputs a message like:
```

With respect to MODEL R LOT
Variation of MAX(V(1)) is negative: -1.000000e-02 (Unit/%) or
1.000000e+00 (%/%)

```

Negative variation means that when parameter is increased, target is decreasing.
3. Then with all the sensitivity data, Eldo computes the combination of min or max parameter values that will generate the best and worst cases (MIN and MAX) for each of the T target.

There can be at most \(2 \times\) T worst case simulations. During these simulations, Eldo does not output anything.
4. Finally, Eldo computes the worst case information for all the targets, and outputs this information.

Thus, there can be at most \(1+\mathrm{P}+2 \times \mathrm{T}\) simulations. Worst Case analysis assumes the influence of each parameter to be linear, and not correlated with other parameters.

The SORT_ parameters are used to limit the amount of output information.

\section*{Parameters}
- DC

Specifies a DC analysis. An analysis type MUST be specified.
- AC

Specifies an AC analysis. An analysis type MUST be specified.
- tran

Specifies a transient analysis. An analysis type MUST be specified.
. wCASE can also be used in Steady-State analysis (.SSt). For more information see .SST (Steady-State Worst Case analysis) of the Eldo RF User's Manual.
- output

Specifies the type of Worst Case Analysis:
MIN
Only the minimum case is extracted.
MAX
Only the maximum case is extracted.
вотн
Both minimum and maximum cases are extracted. Default=вотн.

\section*{- Vary}

Specifies the kind of variation; Dev, цот or вотн. Default=вотн.
- TOL

Specifies that a variation or tolerance is to be applied to the sensitivity measurement.
- VAL

The percentage tolerance value for the sensitivity: <value>. Default=2\%. If in the .chi file Eldo states that sensitivity is zero, this may be due to the rol value being set too small.
- all

Causes all intermediate waves will be plotted/printed. This can result in large output ASCII/Binary files, depending on the number of waves and the number of Worst Case runs.
- SORT_REL

Only devices with a contribution to the output greater than the value:
SORT_RELX<MAX_variation_on_output> will be listed. The default value of SORT_REL is 0.001 , which means that all devices contributing to more than \(1 / 1000\) of the maximum variation will be listed.
- SORT_ABS

Used to specify the absolute threshold, below which contributors will not be listed. Default value is 0 .
- SORT_NBMAX

Allows the user to limit the list of contributors to a certain value. By default, all contributors are listed.

\section*{Note}

The sorting parameters are additive, that is, their respective effects are cumulative. For example, to create a report with only devices contributing to \(10 \%\) or more of the maximum output deviation and have 15 contributors at most you would specify:
SORT_REL=0.1
SORT_NBMAX=15.

\section*{Related options}

CARLO_GAUSS (see "CARLO_GAUSS" on page 975), SIGTAIL (see "SIGTAIL=VAL" on page 982), STATISTICAL (see "STATISTICAL=0|1" on page 982), DISPLAY_CARLO ("DISPLAY_CARLO" on page 999)

\section*{Example}
```

Worst Case analysis example

* circuit: RC filter
r1 in out rmod 10k
c1 out 0 cmod 1p
vin in 0 ac 1
.model rmod res dev=10%
.model cmod cap dev=10%
* extract cutoff frequency at -3 dB
.extract xycond (xaxis, vdb(out)<=max(vdb(out))-3)
.wcase ac
.ac dec 10 1 1G
.plot ac vdb(out) vp(out)
.end

```

The following results will be obtained in the .chi file:
Sensitivity:
```

With respect to MODEL RMOD DEV: Object :R1
Variation of XYCOND(XAXIS, ...) is negative: -1.598533e+05 (Unit/%)
With respect to MODEL CMOD DEV: Object :C1
Variation of XYCOND(XAXIS, ...) is negative: -1.598533e+05 (Unit/%)

```

Worst case values:
```

*XYCOND (XAXIS, ...) NOM: 1.587800E+0 MIN: 1.312462E+0 MAX: 1.959982E+07

```

Note
If incorrectly used, run times for this command may become excessive, especially where results are completely out of range. LOT/DEV parameters must be applied correctly to devices/models to get reasonable results.

\section*{.WIDTH}

\section*{Set Printer Paper Width}
.WIDTH OUT=80|132
Sets the paper width in number of characters of the output print device.
When multiple occurrences of the .WIDTн command are specified, a warning is issued. The last . WIDTH command will override all previous commands.

\section*{Parameters}
- OUT=80

Specifies that the number of columns or characters on the output device is 80 .
- OUT=132

Specifies that the number of columns or characters on the output device is 132 . The default value is 132 .

\section*{Example}
```

.width out=80

```

Sets the output width on the output device to 80 columns.
```

.WIDTH OUT=80
.WIDTH OUT=132

```

Sets the output width on the output device to 132 columns, as the previous command is ignored.

\section*{Chapter 11 Simulator and Control Options}

\section*{Introduction}

The . option command allows the user to modify Eldo execution behavior by allowing the setting of parameter values other than the default ones.

Multiple . OPTION commands can be used in a netlist. A single . OPTION statement can contain multiple options in any combination and any order.

If an option is stated more than once, the last specified value is used. Unless otherwise described, if an option is not stated, it defaults to zero.

\section*{Eldo Options .OPTION}

\author{
.OPT[ION] OPTION[=VAL] \{OPTION[=VAL]\}
}

The option descriptions have been divided into sections according to what area of the program they affect.

\section*{Note}

\(\square\)
Options from the SPICE language that are not included in the following list are ignored by Eldo.

\section*{Parameters}
- OPTION [=VAL]

The following tables show a list of the possible options which can be used with the . OPTION command. Click on an option to jump to the detailed description of that option. Each option is described in greater detail in this chapter.

The first table lists all the options in alphabetical order. The following tables list the options divided into categories.

Table 11-1. Eldo Options
\begin{tabular}{|l|l|l|l|}
\hline ABSTOL & ABSVAR & ACCSEMICOL & ACDERFUNC \\
\hline ACM & ACOUT & ACSIMPROG & ADJSTEPTRAN \\
\hline ADMS_FAST_PARSE & ADMSBS & AEX & AIDSTP \\
\hline ALIGNEXT & ALTER_ADDSTEP & \begin{tabular}{l} 
ALTER_NOMINAL_ \\
TEXT
\end{tabular} & ALTER_SUFFIX \\
\hline ALTERELDO & ALTINC & AMMETER & ANALOG \\
\hline ASCII & ASCII=val & ASCIIPLOT & ASPEC \\
\hline AUTOSTOP & AUTOSTOPMODULO & BE & BLK_SIZE \\
\hline BLOCKS=IEM & BLOCKS=NEWTON & BSIM3VER & BSLASHCONT \\
\hline CAPANW & CAPTAB & CARLO_GAUSS & CHECKDUPL \\
\hline CHGTOL & CKDCPATH & \begin{tabular}{l} 
COLLAPSE_DSPF_ \\
OUTPUT
\end{tabular} & COMPAT \\
\hline COMPEXUP & COMPMOD & COMPNET & CONTINUE_INCLUDE \\
\hline CONTINUOUS_FFT & COU & CPTIME & CSDF \\
\hline CSHUNT & CTEPREC & D2DMVL9BIT & DCLOG \\
\hline DCPART & DCSIMPROG & DEFA2D & DEFAD \\
\hline
\end{tabular}

Table 11-1. Eldo Options
\begin{tabular}{|c|c|c|c|}
\hline DEFAS & DEFAULTFALLTIME & DEFAULTRISETIME & DEFCONVMSG \\
\hline DEFD2A & DEFL & DEFNRD & DEFNRS \\
\hline DEFPD & DEFPS & DEFPTNOM & DEFRMSNTR \\
\hline DEFW & DICPRIO & DIGITAL & DISPLAY_CARLO \\
\hline DOTNODE & DPTRAN & DSCGLOB & DSPF_LEVEL \\
\hline DUMP_EXTRACT & DUMP_FILE_LIST & DUMP_MCINFO & DVDT \\
\hline DYND2ALOG & DYND2ALOG2 & ELDOMOS & EMPTY_MCHISTO \\
\hline ENGNOT & EPS & EPSO & ERR0DIV0 \\
\hline EXTCGS & EXTERR & EXTFILE & EXTMKSA \\
\hline EXTMOD_GENWAVE & EXTRACT_EVAL_ FINAL & EXTRACT_VECT_ AXIS & FALL_TIME \\
\hline FASTRLC & FLICKER_NOISE & FLOATGATE0 & FLOATGATECHECK \\
\hline FLOATGATERR & FLUXTOL & FNLEV & FREQSMP \\
\hline FROM_TO & FS_PARTITIONING & FS_PARTITION_ DEBUG & FS_SOLVE_AMS_ NODES \\
\hline FSDB & FSDB_SINGLE_FILE & FT & GEAR \\
\hline GENK & GMIN & GMIN_BJT_SPICE & GMINDC \\
\hline GNODE & GRAMP & GSHUNT & HACC \\
\hline HIER_SCALE & HIGHVOLTAGE & HIGHVTH & HISTLIM \\
\hline HISTO_ZERO & HMAX & HMIN & HRISEFALL \\
\hline IBIS_SEARCH_PATH & ICDC & ICDEV & IEM \\
\hline IKF2 & INCLIB & INFODEV & INFOMC \\
\hline INFOMOD & INGOLD & INPUT & INTERP \\
\hline ITL1 & ITL3 & ITL4 & ITL6 \\
\hline ITL7 & ITL8 & ITOL & ITRPRT \\
\hline JTHNOISE & JWDB & JWDB_ACTRAN_ USE_TIME & JWDB_EVENT \\
\hline JWDB_EXTENSIONS & JWDB_PERCENT & KEEP_DSPF_NODE & KEEP_HMPFILE \\
\hline KEEPDANGLING & KEEPSHORTED & KLIM & KWSCALE \\
\hline LCAPOP & LIBINC & LICN & LIMNWRMOS \\
\hline LIMPROBE & LIST & LOCAL_NOWARN & LOOPV0 \\
\hline LOWVOLTAGE & LOWVTH & LVLTIM & \begin{tabular}{l}
LVS_IGNORE_ \\
VARIABLE
\end{tabular} \\
\hline M53 & MACMOD & MAX_CHECKBUS & MAX_DSPF_PLOT \\
\hline
\end{tabular}

Table 11-1. Eldo Options
\begin{tabular}{|c|c|c|c|}
\hline MAXADS & MAXL & MAXNODEORD & MAXNODES \\
\hline MAXORD & MAXPDS & MAXSTEP & MAXTOTWARN \\
\hline MAXTRAN & MAXV & MAXW & MAXWARN \\
\hline MC_IGNORE_BINNING & MC_NOMINAL_OP & MEAS_TARGWHEN & MEASFILE \\
\hline METHOD=GEAR & MINADS & MINL & MINPDS \\
\hline MINRACC & MINRESISTANCE & MINRVAL & MINW \\
\hline MIXEDSTEP & MMSMOOTH & MMSMOOTHEPS & MNUMER \\
\hline MOD4PINS & MODMONTE & MODWL & MODWLDOT \\
\hline MOTOROLA & MSGBIAS & MSGNODE & MTHREAD \\
\hline NETSIZE & NEWACCT & NEWTON & NGATEDEF \\
\hline NGTOL & NMAXSIZE & NO_FS_VA & NOACDERFUNC \\
\hline NOACT0 & NOADMSBS & NOAEX & NOALTINCEX \\
\hline NOASCII & NOASCIIPLOT & NOAUTOCTYPE & NOBOUND_PHASE \\
\hline NOBSLASHCONT & NOCATMX & NOCKRSTSAVE & NOCMPUNIX \\
\hline NOCONVASSIST & NOCOU & NODCINFOTAB & NODCPART \\
\hline NODCPOWNEG & NODE & NODEFNEWTON & NODEFRMSNTR \\
\hline NODUPINSTERR & NOELDOLOGIC & NOELDOSWITCH & \begin{tabular}{l}
NOERR \\
XPINSMISMATCH
\end{tabular} \\
\hline NOEXTRACTCOMPLEX & NOFNSIEM & NOICNODE & NOIICXNAME \\
\hline NOINIT & NOISE_SGNCONV & NOJWDB & NOKEYWPARAMSST \\
\hline NOKWSCALE & NOLAT & NOLICN & NOLTEDISC \\
\hline NOMATSING & NOMEMSTP & NOMOD & NOMODWL \\
\hline NONOISE & NONWRMOS & NOOP & NOPAGE \\
\hline NOPROBEOP & NOQTRUNC & NORMOS & NOSETBUSEXPAND \\
\hline NOSIZECHK & NOSMKMCWC & NOSSTKEYWORD & NOSTATP \\
\hline NOSWITCH & NOTRC & NOTRCLIB & NOVATOPOCHK \\
\hline NOWARN & NOWAVECOMPLEX & NOXTABNOISE & NOZSINXX \\
\hline NSAFILE_FORMAT & NUMDGT & NWRMOS & OPALLDC \\
\hline OPSELDO_ABSTRACT & OPSELDO_DETAIL & OPSELDO_DISPLAY_ GOALFITTING & OPSELDO_FORCE_ GOALFITTING \\
\hline OPSELDO_JWDB_RUN & OPSELDO_NETLIST & \begin{tabular}{l}
OPSELDO \\
NO_DUPLĪCATE
\end{tabular} & \[
\begin{aligned}
& \text { OPSELDO_- } \\
& \text { NOGOALFITTING }
\end{aligned}
\] \\
\hline OPSELDO_OUTER & OPSELDO_OUTPUT & OPTYP & OSR \\
\hline OUT_ABSTOL & OUT_REDUCE & OUT_RELTOL & OUT_RESOL \\
\hline
\end{tabular}

Table 11-1. Eldo Options
\begin{tabular}{|c|c|c|c|}
\hline OUT_SMP & OUT_STEP & PARAM_BEFORE_USE & PARAMETRIC ACTRAN \\
\hline PARAMOPT NOINITIAL & PARHIER & PARTGATE_AMS_ALL & PARTVDD \\
\hline PARTVDD_AMS_ALL & PATTERN_MAX ALLOWED_COEFF & PCS & PCSPERIOD \\
\hline PCSSIZE & PEVFLY & PGATEDEF & PIVCHECK \\
\hline PIVREL & PIVTOL & PODEV & POST \\
\hline POST_DOUBLE & POWNEG0 & PRINT_ACOP & PRINTFILE_STEP \\
\hline PRINTFILE_FREQ_
STEP STEP & PRINTFILE_TIME_ STEP & PRINTLG & PROBE \\
\hline PROBEOP & PROBEOP2 & PROBEOPX & PSF \\
\hline PSF_ALL_FILES & PSF_FULLNAME & PSF_NODEVICE_ NOISE & PSF_SCALARDC \\
\hline PSF_VERSION & PSF_WRITE_ALL & PSFASCII & PSOSC \\
\hline PSTRAN & QTRUNC & QUOTREL & QUOTSTR \\
\hline RAILINDUCTANCE & RAILRESISTANCE & RANDMC & RATPRINT \\
\hline REDUCE_KEEP_INST & REDUCE_KEEP_NODE & \[
\begin{array}{|l}
\text { REDUCE_KEEP_ } \\
\text { OUTPUTS }
\end{array}
\] & REDUCE_MAX_CAP \\
\hline REDUCE_MAX_IND & REDUCE_MAX_RES & REDUCE & RELTOL \\
\hline RELTRUNC & RELVAR & \[
\begin{array}{|l}
\hline \text { RESET_MULTIPLE_R } \\
\text { UN }
\end{array}
\] & RESNW \\
\hline RGND & RGNDI & RISE_TIME & RMMINRVAL \\
\hline RMOS & RSMALL & RZ & SAMPLE \\
\hline SAVETIME & SCALE & SCALEBSIM & SCALM \\
\hline SDA & SEARCH & SHRINK_FACTOR & SIGTAIL \\
\hline SIMUDIV & SLASHCONT & SMOOTH & SOIBACK \\
\hline SPI3ASC & SPI3BIN & SPI3NOCOMPLEX & SPICEDC \\
\hline SPIOUT & SPLITC & SPMODLEV & STARTSMP \\
\hline STAT & STATISTICAL & STEP & STOPONFIRSTERROR \\
\hline STRICT & SUBALEV & SUBFLAGPAR & TEMP_UNIT \\
\hline TEMPCOUK & THERMAL_NOISE & TIMEDIV & TIMESMP \\
\hline TMAX & TMIN & TNOM & TPIEEE \\
\hline TRAP & TRTOL & TUNING & ULOGIC \\
\hline UNBOUND & USEDEFAP & USE_LOCATION_MAP & \[
\begin{aligned}
& \text { USE_SPECTRE_ } \\
& \text { CONSTANT }
\end{aligned}
\] \\
\hline
\end{tabular}

Table 11-1. Eldo Options
\begin{tabular}{|l|l|l|l|}
\hline USEFIRSTDEF & USETHREAD & VBCSAT & VERBOSE \\
\hline VMAX & VAMAXEXP & VMIN & VNTOL \\
\hline \begin{tabular}{l} 
VOLTAGE_LOOP_ \\
SEVERITY
\end{tabular} & VXPROBE & WARN2ERR & \begin{tabular}{l} 
WARNING__ \\
DEVPARAM
\end{tabular} \\
\hline WARN & WARNMAXV & WBULK & WDB_IDELTA \\
\hline WDB_VDELTA & WDB_NOSYNCHRO & WL & \begin{tabular}{l} 
WRITE_ALTER_ \\
NETLIST
\end{tabular} \\
\hline WSF & WSFASCII & XA & XBYNAME \\
\hline YMFACT & ZCHAR & ZDETECT & ZOOMTIME \\
\hline
\end{tabular}

Options divided into categories:
Table 11-2. Simulator Compatibility Options
\begin{tabular}{|l|l|l|l|}
\hline COMPAT & COMPMOD & COMPNET & MOTOROLA \\
\hline SDA & SPI3ASC & SPI3BIN & SPI3NOCOMPLEX \\
\hline SPICEDC & SPIOUT & \begin{tabular}{l} 
USE_SPECTRE_ \\
CONSTANT
\end{tabular} & WSF \\
\hline WSFASCII & & & \\
\hline
\end{tabular}

Table 11-3. Netlist Parser Control Options
\begin{tabular}{|l|l|l|l|}
\hline ACCSEMICOL & ADMS_FAST_PARSE & ADMSBS & ALTER_ADDSTEP \\
\hline ALTERELDO & ALTINC & BSLASHCONT & CHECKDUPL \\
\hline CKDCPATH & COMPEXUP & CONTINUE_INCLUDE & DICPRIO \\
\hline DOTNODE & ERR0DIV0 & EXTERR & KEEPDANGLING \\
\hline KEEPSHORTED & LOOPV0 & MACMOD & MEAS_TARGWHEN \\
\hline MTHREAD & NOALTINCEX & NOACT0 & NOADMSBS \\
\hline NOBSLASHCONT & PARAM_BEFORE_USE & PARHIER & \begin{tabular}{l} 
NOERR_- \\
XPINSMISMATCH
\end{tabular} \\
\hline NOKEYWPARAMSST & NOMATSING & NOSETBUSEXPAND & NOSSTKEYWORD \\
\hline NOZSINXX & POWNEG0 & QUOTREL & PATTERN_MAX_ \\
\hline ALLOWED_COEFF \\
\hline REVFLY & SLASHCONT & STOPONFIRSTERROR & STRICT \\
\hline SUBALEV & SUBFLAGPAR & WSEFIRSTDEF & USETHREAD \\
\hline USE_LOCATION_MAP & \begin{tabular}{l} 
VOLTAGE_LOOP_ \\
SEVERITY
\end{tabular} & XBYNAME \\
\hline
\end{tabular}

Table 11-4. Simulation Speed, Accuracy and Efficiency Options
\begin{tabular}{|c|c|c|c|}
\hline ABSTOL & ABSVAR & ADJSTEPTRAN & AIDSTP \\
\hline CAPANW & CHGTOL & DVDT & EPS \\
\hline FASTRLC & FLUXTOL & FREQSMP & FROM_TO \\
\hline FT & HACC & HMAX & HMIN \\
\hline HRISEFALL & INCLIB & ITL1 & ITL3 \\
\hline ITL4 & ITL6 & ITL7 & ITL8 \\
\hline ITOL & LIBINC & LIMNWRMOS & LVLTIM \\
\hline MAXNODES & MAXSTEP & MAXTRAN & MAXV \\
\hline NETSIZE & NGTOL & NMAXSIZE & NOCONVASSIST \\
\hline NODCPOWNEG & NOLAT & NONWRMOS & NOQTRUNC \\
\hline NOSWITCH & PCS & PCSSIZE & PCSPERIOD \\
\hline PIVCHECK & PIVREL & PIVTOL & PSOSC \\
\hline QTRUNC & RATPRINT & RELTOL & RELTRUNC \\
\hline RELVAR & SAMPLE & SPLITC & STARTSMP \\
\hline STEP & TIMESMP & TRTOL & TUNING \\
\hline UNBOUND & VMAX & VMIN & VNTOL \\
\hline WDB_IDELTA & WDB_VDELTA & WDB_NOSYNCHRO & XA \\
\hline
\end{tabular}

Table 11-5. Miscellaneous Simulation Control Options
\begin{tabular}{|l|l|l|l|}
\hline AMMETER & AUTOSTOP & AUTOSTOPMODULO & CARLO_GAUSS \\
\hline CPTIME & DEFAULTFALLTIME & DEFAULTRISETIME & DEFPTNOM \\
\hline DSCGLOB & DSPF_LEVEL & FALL_TIME & FLOATGATE0 \\
\hline FLOATGATECHECK & FLOATGATERR & HIGHVOLTAGE & HIGHVTH \\
\hline ICDC & ICDEV & INTERP & LICN \\
\hline LOWVOLTAGE & LOWVTH & \begin{tabular}{l} 
LVS_IGNORE_VARIAB \\
LE
\end{tabular} & M53 \\
\hline \begin{tabular}{l} 
MC_IGNORE_ \\
BINNING
\end{tabular} & MMSMOOTH & MMSMOOTHEPS & NOICNODE \\
\hline NOLICN & POLTEDISC & NOMEMSTP & \begin{tabular}{l} 
PARAMOPT_ \\
NOINITIAL
\end{tabular} \\
\hline NOVATOPOCHK & RISE_TIME & SIGTAIL & RGND \\
\hline RGNDI & & & STATISTICAL \\
\hline
\end{tabular}

Table 11-5. Miscellaneous Simulation Control Options
\begin{tabular}{|l|l|l|l|}
\hline TEMP_UNIT & TNOM & TPIEEE & ULOGIC \\
\hline ZOOMTIME & & & \\
\hline
\end{tabular}

Table 11-6. Model Control Options
\begin{tabular}{|l|l|l|l|}
\hline ACDERFUNC & ACM & ASPEC & BSIM3VER \\
\hline DEFAD & DEFAS & DEFL & DEFNRD \\
\hline DEFNRS & DEFPD & DEFPS & DEFW \\
\hline ELDOMOS & FNLEV & GMIN & GMIN_BJT_SPICE \\
\hline GMINDC & KWSCALE & GENK & HIER_SCALE \\
\hline KLIM & MAXPDS & IBIS_SEARCH_PATH & MAXADS \\
\hline MAXL & MINW & MAXW & MINADS \\
\hline MINL & MODWL & MINRACC & MINRESISTANCE \\
\hline MINRVAL & NOAUTOCTYPE & NOCATMX & MOD4PINS \\
\hline MODMONTE & PGATEDEF & RAILINDUCTANCE & RAILRESISTANCE \\
\hline NOACDERFUNC & RESNW & RMMINRVAL & RMOS \\
\hline NWRMOS & RZ & SCALE & SCALEBSIM \\
\hline REDUCE & SHRINK_FACTOR & SOIBACK & SPMODLEV \\
\hline RSMALL & TMIN & USEDEFAP & \begin{tabular}{l} 
WARNING_ \\
DEVPARAM
\end{tabular} \\
\hline SCALM & WL & YMFACT & ZDETECT \\
\hline TMAX & WARNMAXV & MADALE & \\
\hline
\end{tabular}

Table 11-7. RC Reduction Options
\begin{tabular}{|l|l|l|l|}
\hline REDUCE_KEEP_INST & REDUCE_KEEP_NODE & \begin{tabular}{l} 
REDUCE_KEEP_ \\
OUTPUTS
\end{tabular} & REDUCE_MAX_CAP \\
\hline REDUCE_MAX_IND & REDUCE_MAX_RES & & \\
\hline
\end{tabular}

Table 11-8. Noise Analysis Options
\begin{tabular}{|l|l|l|l|}
\hline FLICKER_NOISE & IKF2 & JTHNOISE & THERMAL_NOISE \\
\hline NOISE_SGNCONV & NONOISE & & \\
\hline
\end{tabular}

Table 11-9. Simulation Display Control Options
\begin{tabular}{|l|l|l|l|}
\hline ACSIMPROG & DCSIMPROG & ENGNOT & INGOLD \\
\hline LOCAL_NOWARN & MAXTOTWARN & MAXWARN & MSGBIAS \\
\hline MSGNODE & NOWARN & NUMDGT & PRINTLG \\
\hline VERBOSE & WARN & WBULK & \\
\hline
\end{tabular}

Table 11-10. Simulation Output Control Options
\begin{tabular}{|c|c|c|c|}
\hline ACOUT & ALTER_NOMINAL_TEXT & ALTER_SUFFIX & ASCII \\
\hline ASCIIPLOT & BLK_SIZE & CAPTAB & COLLAPSE_DSPF_OU TPUT \\
\hline CONTINUOUS_FFT & DEFRMSNTR & DISPLAY_CARLO & DUMP_EXTRACT \\
\hline DUMP_MCINFO & EMPTY_MCHISTO & EXTCGS & EXTFILE \\
\hline EXTMKSA & EXTMOD_GENWAVE & \begin{tabular}{l}
EXTRACT_EVAL_ \\
FINAL
\end{tabular} & \[
\begin{aligned}
& \text { EXTRACT_VECT_ } \\
& \text { AXIS }
\end{aligned}
\] \\
\hline HISTLIM & HISTO_ZERO & INPUT & INFOMC \\
\hline JWDB_ACTRAN_USE_ TIME & JWDB_EVENT & JWDB_EXTENSIONS & JWDB_PERCENT \\
\hline KEEP_DSPF_NODE & KEEP_HMPFILE & LCAPOP & LIMPROBE \\
\hline LIST & MAX_CHECKBUS & MAX_DSPF_PLOT & MC_NOMINAL_OP \\
\hline MEASFILE & NEWACCT & NOASCII & NOASCIIPLOT \\
\hline NOBOUND_PHASE & NODCINFOTAB & NODE & NODEFRMSNTR \\
\hline NOEXTRACTCOMPLEX & NOMOD & NOOP & NOPAGE \\
\hline NOSIZECHK & NOSMKMCWC & NOSTATP & NOTRC \\
\hline NOTRCLIB & NOWAVECOMPLEX & NOXTABNOISE & OPALLDC \\
\hline OPTYP & OUT_RESOL & OUT_SMP & OUT_STEP \\
\hline \begin{tabular}{l}
PARAMETRIC_ \\
ACTRAN
\end{tabular} & POST & PRINT_ACOP & PRINTFILE_STEP \\
\hline PRINTFILE_FREQ_ STEP & PRINTFILE_TIME_ STEP & SIMUDIV & STAT \\
\hline TEMPCOUK & TIMEDIV & VBCSAT & VXPROBE \\
\hline WRITE_ALTER_ NETLIST & & & \\
\hline
\end{tabular}

Table 11-11. Optimizer Output Control Options
\begin{tabular}{|l|l|l|l|}
\hline OPSELDO_ABSTRACT & OPSELDO_DETAIL & \begin{tabular}{l} 
OPSELDO_DISPLAY_ \\
GOALFITTING
\end{tabular} & \begin{tabular}{l} 
OPSELDO_FORCE_ \\
GOALFITTING
\end{tabular} \\
\hline OPSELDO_JWDB_RUN & OPSELDO_NETLIST & \begin{tabular}{l} 
OPSELDO_- \\
NO_DUPLICATE
\end{tabular} & \begin{tabular}{l} 
OPSELDO_- \\
NOGOALFITTING
\end{tabular} \\
\hline OPSELDO_OUTER & OPSELDO_OUTPUT & RESET_MULTIPLE_RUN & \\
\hline
\end{tabular}

Table 11-12. File Generation Options
\begin{tabular}{|l|l|l|l|}
\hline AEX & ALIGNEXT & ASCII=val & COU \\
\hline CSDF & DUMP_FILE_LIST & FSDB & FSDB_SINGLE_FILE \\
\hline INFODEV & INFOMOD & ITRPRT & JWDB \\
\hline NOAEX & NOCKRSTSAVE & NOCOU & NOIICXNAME \\
\hline NOJWDB & NOPROBEOP & NSAFILE_FORMAT & OUT_ABSTOL \\
\hline OUT_REDUCE & OUT_RELTOL & PROBE & PROBEOP \\
\hline PROBEOP2 & PROBEOPX & PSF & PSF_ALL_FILES \\
\hline PSF_FULLNAME & \begin{tabular}{l} 
PSF_NODEVICE_ \\
NOISE
\end{tabular} & PSF_SCALARDC & PSF_VERSION \\
\hline PSF_WRITE_ALL & PSFASCII & SAVETIME & \\
\hline
\end{tabular}

Table 11-13. Mathematical Algorithm Options
\begin{tabular}{|l|l|l|l|}
\hline ANALOG & BE & BLOCKS=IEM & BLOCKS=NEWTON \\
\hline CSHUNT & DCPART & DIGITAL & DPTRAN \\
\hline GEAR & GNODE & GSHUNT & IEM \\
\hline MAXORD & METHOD=GEAR & NEWTON & NODCPART \\
\hline NODEFNEWTON & NORMOS & OSR & PSTRAN \\
\hline SMOOTH & TRAP & & \\
\hline
\end{tabular}

Table 11-14. Mixed-Mode Options
\begin{tabular}{|l|l|l|l|}
\hline D2DMVL9BIT & DEFA2D & DEFD2A & DEFCONVMSG \\
\hline DYND2ALOG & DYND2ALOG2 & FS_SOLVE_AMS_NODES & FS_PARTITIONING \\
\hline \begin{tabular}{l} 
FS_PARTITION_ \\
DEBUG
\end{tabular} & MIXEDSTEP & NO_FS_VA & PARTGATE_AMS_ALL \\
\hline PARTVDD & PARTVDD_AMS_ALL & & \\
\hline
\end{tabular}

Table 11-15. Other Options
\begin{tabular}{|l|l|l|l|}
\hline CTEPREC & DCLOG & EPSO & MAXNODEORD \\
\hline NODUPINSTERR & NOELDOSWITCH & NOFNSIEM & NOINIT \\
\hline SEARCH & VAMAXEXP & ZCHAR & \\
\hline
\end{tabular}

\section*{Cadence Compatibility Options}
- SDA

When set to 2 , this parameter enables Cadence wSF compatible ASCII or binary output files for EDGE and OPUS. See wsF and wsfascil options. WSF is only supported on the Solaris platform. This option requires license authorization. Default is 0 .
- wSF

When SDA=2, Eldo creates a Cadence wsF binary output (.wsf) file for EDGE and OPUS. WSF is only supported on the Solaris platform. This option requires license authorization.
- wSFASCII

When SDA=2, Eldo creates a Cadence wSF ASCII output (.wsf) file for EDGE and OPUS. WSF is only supported on the Solaris platform. This option requires license authorization.

\section*{SPICE Compatibility Options}
- SPi3ASC

Forces Eldo to create a SPICE3 compatible ASCII output (.spi3) file.
- SPi3bin

Forces Eldo to create a SPICE3 compatible binary output (.spi3) file.
- SPI3NOCOMPLEX

Allows to choose which format should be used for the SPICE3 compatible binary output (.spi3) file header in AC analysis. By default, complex names are written (v(out)). If this option is specified, Eldo switches to pre-v6.6 behavior, that is, \(\operatorname{vr}\) (out) and vi(out) are written.
- SPICEDC

Forces Eldo to use the Berkeley SPICE mechanism when calculating the DC operating point rather than using the normal method. By using this method, VBE junctions of BJTs are set to 0.7 V , while voltages across other PN junctions are set to 0 V . This option can increase the efficiency on circuits containing BJT elements.
- Spiout

DC operating point is sorted alphanumerically.

\section*{Simulator Compatibility Options}
- COMPAT

This is equivalent to the -compat flag used when invoking Eldo. Provides HSPICE compatibility. Note this option must be set at the top of the design, otherwise results can be unpredictable. Option COMPAT is equivalent to setting both COMPMOD and COMPNet options shown below:
- COMPMOD

Triggers only the automatic conversion of models. Provides HSPICE models compatibility. This is equivalent to the -compmod flag used when invoking Eldo.
- COMPNET

Causes the netlist to be interpreted as compatible format, but the models themselves are treated as Eldo SPICE models. This means it is assumed that models are already Eldo models. Provides HSPICE netlist compatibility. This is equivalent to the -compnet flag used when invoking Eldo.

\section*{(1) Please refer to the "HSPICE Compatibility" on page 1373 for further information.}
- motorola

Invokes the Motorola (SSIM model) mode of Eldo. This option is equivalent to the -ssim command-line flag of Eldo. This model is only supported on Solaris platforms in Eldo 32-bit mode. See also "Motorola SSIM Model (Eldo Level 54 or SSIM)" on page 276.
- USE_SPECTRE_CONSTANT

Allows Eldo to understand a number of Spectre default parameters, constants, and functions. See "Spectre Default Constants and Functions" on page 1398 for further information.

\section*{Netlist Parser Control Options}
- ACCSEMICOL

Forces Eldo to consider the semicolon character ';' in a netlist as a regular character. By default, the semicolon character ';' in a netlist is considered a space. Some netlisters exist which make use of this character for node names.
- ADMS_FAST_PARSE

This option is used to accelerate the elaboration phase of the design with Questa ADMS. Please refer to Black-Box Mode for Eldo and ADiT in the Questa ADMS User's Manual for further information.

\section*{- ADMSBS}

This option enables extended identifiers to be used in VHDL-AMS descriptions. This option is used, and set by default, with Questa ADMS. It is possible to disable this by using specifying noadmsbs.
- ALTER_ADDSTEP

Appends . STEP commands found in .ALTER statements, instead of substituting. By default, Eldo substitutes the . STEP commands in the main netlist by those found in .ALTER statements.
- altereldo

Changes the way the .ALTER re-run feature works in compat mode. In compat mode, for alter index ' \(n\) ', Eldo revisits the ' \(n-1\) ' alter looking for substitution. In default Eldo mode, for alter index ' \(n\) ', Eldo only deals with the nominal and the alter ' \(n\) '; it ignores the ' \(n-1\) ' alter. In other words, in compat mode, alters are cumulative, but not in Eldo default mode. Specify altereldo to activate the default Eldo mode behavior when in compat mode.
- altinc

Forces Eldo to replace the first . INClude statement found in an input netlist by the first . include statement found in the .alter section of the netlist. This allows the replacement of one file by another one when using the Eldo re-run facility.
- BSLASHCONT

Allows two backslashes to be used for the continuation of the line. Example:
```

.option BSLASHCONT
R1 1 2 <br>
3k
R2 1 2 1k

```

R1 will be set to 3 K .
- Checkdupl

Forces Eldo to perform the check of duplicate instance names, even when the netlist is larger than the internal limit ( 1000 lines). This option is position-dependent, it takes affect only after it has been set in the netlist, if the option is set at the end of the netlist it will have no effect.
- CKDCPATH

Forces Eldo to issue a warning instead of an error when a dangling node (no DC path to ground) is encountered on a current source. The source is then disabled and the node connected to ground. This option is only used in -compat mode.
- COMPEXUP

Forces Eldo to keep the name of the extraction results (from . Extract and .meas statements) in uppercase when in simulator compatibility (-compat) mode. Prior to Eldo v6.6 the names were always in uppercase, beginning Eldo v6.6 they are in lowercase.
- CONTINUE_INCLUDE

Specifies that continuation lines with + as the first character apply to the . Include command in the file. For example, if the main netlist has the two lines:
```

.include file.inc

+ b=2

```

With this option specified, if file file.inc contains as its last line:
```

.param a=1

```

Eldo would interpret this as:
```

.param a=1
+b=2

```
- DICPRIO

Forces . IC statements on nodes to have priority over any coming from a . USE command. By default, if .USE file_name IC is specified in the netlist, and there are also some . IC statements on nodes, then nodes emulated via the .USE command have higher priority than those on . Ic statements.
- DOtnode

Forces Eldo to accept non-hierarchical characters in node names. Must be set if you want to have node \(a .0\) created as a regular node. For backward compatibility. In versions up to 2006.x, Eldo accepted a non-hierarchical node name containing the hierarchical character (usually '.'), providing that the node name did not begin with an X. For instance, foo.l was accepted as a node name, but \(X 1.1\) was recognized as a hierarchical node and therefore Eldo expected a local node named " 1 " in subckt \(X 1\). However because ADMS subcircuit instances do not necessarily begin with an X, the possibility of having the hierarchical character in node name is not allowed in ADMS, which can lead to incompatibility between Eldo and ADMS. The hierarchical character in non-hierarchical names is not allowed (beginning 2007.1), so that Eldo and ADMS conventions match. In ADMS, this option will be ignored.
- ERRODIVO=0|1

When set to 1 , this forces Eldo to return an error for a zero divided by zero calculation. Default is 0 . By default, \(0 / 0\) returns zero.

\section*{- exterr}

Forces Eldo to stop and generate errors when there are problems found in .Extract or . meas commands. By default, Eldo only generates warnings when errors are found in . Extract or .meas commands. Such statements will be ignored. Prior to Eldo v6.7 errors were always generated.
- KEEPDANGLING

Maintains dangling objects in the Eldo database. By default, Eldo disregards dangling objects and shorted MOS, diodes, resistors and capacitors. This can create problems with DSPF because not all objects might be retrieved. Dangling and shorted objects could be the
result of dummy devices added to improve device matching. Parasitics of such devices are required.

\section*{- KEEPSHORTED}

Maintains shorted objects in the Eldo database. By default, Eldo disregards dangling objects and shorted MOS, diodes, resistors and capacitors (objects for which all pins are the same). This can create problems with DSPF because not all objects might be retrieved. Dangling and shorted objects could be the result of dummy devices added to improve device matching. Parasitics of such devices are required.
- LOOPVo

By default, Eldo issues an error (27) when it detects a voltage loop. Use this option to force Eldo to allow a voltage loop or inductor loop of a zero voltage source. Such loops could be generated from an automatic circuit extraction. When specified, any attempt to change the value of one of the sources in a loop will result in an Eldo error. See option
VOLTAGE_LOOP_SEVERITY to downgrade a voltage loop error to a warning.
Rules on Eldo reporting of voltage loops:
- For a single device with two pins shorted:

By default, for a single device with two pins shorted, Eldo issues an error when one of the following conditions is met:
- the source value is positive, for example:
```

v1 n1 n2 10

```
- the source value depends upon a parameter, for example:
```

v1 n1 n2 p1

```
- the source has a total loop voltage of 0 , for example:
```

v1 n1 n2 0

```

No error is issued for this scenario if option Loopvo is set.
In compat mode (-compat flag or option COMPAt), no error will be issued.
- For two or more inductors or voltage sources connected in such a way they form a loop:
- To downgrade an error to a warning, specify option voltage_LOOP_SEVERITY= warning. Default is ERror.
- If all the source values in the loop are zero then use option Loopvo to disable the checks as in the case of a single device, for example:
```

v1 n1 n2 0
v2 n1 n2 0

```
- If one of the voltage loop values is different from zero an error will be issued unless option VOLTAGE_LOOP_SEVERITY= WARNING is set, for example:
```

v1 n1 n2 0
v2 n1 n2 1

```

In this example the checks cannot be disabled by option LOOPvo.
In compat mode (-compat flag or option COMPAт), you cannot override the error (option LOOPvo).
- MACMOD=[1|2|3|0]

Extended MOSFET element support. Enables MOSFET elements access to subcircuit definitions or Verilog-A models when there is no when there is no corresponding model reference on the . MODEL statement. It also enables a subcircuit (X) instance access to a model reference when there is no corresponding subcircuit definition or Verilog-A module. Option MACMOD is equivalent to option MACMOD=1.

In other words, if Mxxx is in a nelist this could be a subckt instance even if the name begins with M. If Xxxx is in a netlist it could be a MOSFET element, a subckt instance, or a Verilog-A module instance.
When a . HDL command (see ".HDL" on page 678) is used to compile a Verilog-A model then it will be instantiated by an X-instance. When macmod is enabled then the X-instance could be a MOSFET.

\section*{MACMOD=1}

For a MOSFET element Mxxx of model name MNAME Eldo will first look for a MOS . model statement with the name MNAME. If a MOS model MNAME is not found Eldo will look for a subckt definition of the name MNAME. If a subckt definition is found Eldo will use it for the Mxxx instance. The number of terminals must match.

\section*{MACMOD=2}

For an X-element (subckt instance or Verilog-A instance) Eldo will first look for a subckt definition or a Verilog-A module. If a subckt definition or a Verilog-A module is not found Eldo will look for a MOS model definition.
```

MACMOD=3

```

Enables both of the above features.
```

MACMOD=0

```

Disables the features. Default.
- MEAS_TARGWHEN

This option affects the interpretation of the targ specification on .meas commands using when statements. By default, Eldo ignores the targ specification. Specify this option to return to the pre-2009.2 behavior for a warning to be generated if targ is used in whentype .meas statements.
- mTHREAD

Activates multi-threading for a single DC or TRAN simulation. Eldo will share computer resources on a multi-processor machine. Eldo will make use of all the possible CPUs on the machine. This option is equivalent to the Eldo -mthread command line flag.

See "Multi-Threading Eldo Simulations" on page 58 for a full description of multithreading in Eldo.
- NOACTO

Forces AC calculation only at the specified timevalues for a combination of .AC with .OP timevalues. Default behavior (without the option) is that an AC analysis is performed at time 0 .
- noAltincex

By default the content of . Include commands specified in .ALTER blocks is treated by Eldo as if the content is written at full length in the netlist and substitutes accordingly. In previous versions (pre-v6.9), the . Include commands specified in .ALTER blocks were added (extended) to the nominal circuit, for example:
```

i1 1 0 1
r1 1 0 1
.op
.extract dc v(1)
.alter
.include altincex.a1
.end

```
assuming file altincex.al contains the line r1 10 2, for the first ALTER run Eldo will substitute r1 101 by r1 102 in the netlist (behaves as if line r1 102 was in the netlist). For Eldo versions before v6.9, Eldo assumed two resistors in parallel to the I1 device. For backward compatibility, specify option nOALTINCEX to switch back to the old mechanism.
- NOADMSBS

Disables option admsbs which is set by default with Questa ADMS. With noadmsbs specified, extended identifiers cannot be used in VHDL-AMS descriptions.
- NOBSLASHCONT

Disables option Slashcont when invoking Eldo with the -compat flag.
- NOCMPUNIX

The characters "[" and "]" are interpreted as special characters when the wildcard character "*" is used. According to Unix convention, these special characters may be overridden by using the backslash character " "" which removes the special function of the character that immediately follows it.
- NOELDOLOGIC

Specifies that subcircuit X instances can be named beginning with any Eldo logic or macro primitive name. With this option, Eldo will not attempt to parse such instances as logic gates. This option is automatically set when invoking Eldo with the -compat flag. This option affects the following Eldo built-in logic primitives: AND, OR, NAND, NOR, XOR, CMP, CMPD, INV; and the following Eldo built-in macromodels: ADC, DAC, DEL, FNS, FNZ, OPA.
- NOERR_XPINSMISMATCH[=subckt_name]

When this option is set, if the X instance contains more pins than the SUBCKT definition, Eldo will allow this but only the first pins in the SUBCKT will be taken into account.
The mismatch in the number of pins will not generate warning/error messages if option nOERR_XPINSMISMATCH is specified without any argument, or if the subckt name matches that specified in the command.

This enhancement works only for Eldo, not ADMS.
- NOMATSING

This option can be used to complete a simulation if the simulation stops with a warning regarding a singularity. Otherwise, it will be stopped if a singularity is found in DC. However, the design has to be improved if there is a singularity. Even if the simulation continues, this does not mean that the solution in DC is correct.
Please refer to the appendix "Improved Diagnostics for Certain Erroneous Models" in the Questa ADMS User's Manual for further information.
- nosetbusexpand

Disables automatic bus expansion inside the .SETBUS command.
- noSStkeyword|

NOKEYWPARAMSST
Tells the parser to bypass the RF keyword check in expressions or in .param. For a full list of Eldo RF keywords that cannot be used in .PARAM, see "Reserved Keywords Not Available in .PARAM if an RF Analysis is Specified in the Netlist" on page 779.
- NOZSINXX

Remove the effect of the \(\sin x / x\) term used in the AC response of Z transforms. The response was modified in Eldo v6.3, previously the term was not taken into account.
- PARAM_BEFORE_USE [=0|1]

When set to 1 , parameters must be defined before being used. Default is 0 . Note that option STRICT sets the value of PARAM_before_uSe to 1 ; it is possible to reset PARAM_BEFORE_USE to 0 after option Strict has been specified. For example:
```

.option STRICT
.OPTION PARAM_BEFORE_USE = 0

```
allows a parameter to be used before its definition, such as in:
```

.PARAM p2 = p1
.param p1 = 1

```
- PARHIER='local'|'global'|'hier'|'hierlocal'

This parameter controls the priorities for parameters. Quotes are optional. Default for Eldo is parhier=hier (was local in pre-v6.6 versions of Eldo). When -compat is set, default is global.

When PARHIER is GLOBAL or LOCAL, then the parameter priorities adopted in X statements are performed as if the operations were executed inside the SUBCKT. The following rules apply:
When PARHIER is GLOBAL, the priority is the following:
1. .PARAM statement at a higher level
2. Value at the X call (instance)

\section*{3. SUBCKT definition}

When PARHIER is LOCAL, the priority is:
1. SUBCKT call (instance)
2. SUBCKT definition
3. .PARAM statement

When PARHIER is set to HIER or HIERLOCAL, then the mechanism for evaluating parameters mimics that of the function call in programming languages such as C . The parameters found on the right-hand side of the expressions are sought first in the current environment, while the name on the left-hand side refers to the parameter name inside the subcircuit being called. This is a very different mechanism than for GLOBAL or LOCAL. For example:
```

ID VDD 0 1m
RC1 S1 VDD 1k
X1 S1 0 sub1
.op
.subckt sub1 c b
.param w = 1k
XM1 c b sub2 w2 = w
.ends sub1
.subckt sub2 c b
.param w = 2k
r1 c b 'w2'
.ends sub2
.param w = 7k
.end

```

If PARHIER \(=\) GLOBAL \(w 2\) is 7 k . Because it is as if we had:
```

XM1 c b sub2 xm1.w2 = xm1.w

```
and xm1.w takes the definition at the highest level.
If PARHIER \(=\) LOCAL w2 is 2 k . Because it is as if we had:
```

XM1 c b sub2 xm1.w2 = xm1.w

```
and xm1.w takes the definition at the lowest level, i.e inside the subcircuit SUB2.

If PARHIER \(=\) HIER w2 is 1 k . Because it is as if we had:
```

XM1 c b sub2 xm1.w2 = w

```
and local value for \(w\) is 1 k .
If PARHIER \(=\) HIERLOCAL w2 is 1 k : same as PARHIER=HIER.
However, in case of PARHIER \(=\) HIER or PARHIER \(=\) HIERLOCAL, if a parameter is specified at the X instance, then this value will have precedence over the local value if any. For example:
```

ID VDD O 1m
RC1 S1 VDD 1k
X1 S1 0 sub1
.op
.subckt sub1 c b
.param w = 1k
XM1 c b sub2 w=3k w2 = w
.ends sub1
.subckt sub2 c b
.param w = 2k
r1 c b 'w2'
.ends sub2
.param w = 7k
.end

```

Here, Eldo will assume that the w on the \(\mathrm{w} 2=\mathrm{w}\) statement is 3 k because w is explicitly specified on the X instance. If \(\mathrm{w}=3 \mathrm{k}\) had not been there, then the local value 1 k would have been taken.

Note that in case a parameter which appears on the right-hand-side of an expression on a X instance has both a value in the current environment, and in the SUBCKT being called, and is not specified on that X instance, then Eldo will issue a warning that the two values exist, just to warn the user about possible problems in the netlist.

The difference between HIER and HIERLOCAL is for the case a parameter which appears on the right-hand-side of an expression on a X instance, is neither specified on the same X call, neither specified on the current environment: if PARHIER is set to HIER, Eldo will issue an error that the parameter is not found, if PARHIER is set to HIERLOCAL, then Eldo will check for this parameter inside the SUBCKT being called, and will use that value if found. For example:
```

ID VDD 0 1m
RC1 S1 VDD 1k
X1 S1 0 sub1
.op
.subckt sub1 c b
XM1 c b sub2 w2 = w
.ends sub1

```
```

.subckt sub2 c b
.param w = 4k
r1 c b 'w2'
.ends sub2

```

If PARHIER is set to HIER, Eldo will issue an error while evaluating \(w 2=w\), because \(w\) is not found in the current environment. If PARHIER is set to HIERLOCAL, Eldo will check inside the sub2 if w exists, and will find it.
- PATTERN_MAX_ALLOWED_COEFF

Changes the limit of the number of bits used in the alternative syntax for a Pattern Function specification. Default is 100 .
- PEVFLY

Evaluate implicit parameter expressions "on the fly" instead of storing them in memory before evaluation. This can save memory.

In case a circuit contains many implicit expressions, for example:
```

V1 1 0 PWL ( {2*p1} {p2} {3*p1} {p2} {4*p1} ... }

```
where the number of couples (time-value, input-value) can be as high as several millions, then the amount of memory used by Eldo to store the implicit expressions can be huge. If option PEVFLY is set, then implicit expressions which are specified at the top level (not in a .SUBCKT) and after the .OPTION, will be evaluated immediately. This will save a lot of memory. Note that this option has some side effects:
- double definition of parameters is not allowed
- a parameter must be defined before it is used in the implicit expressions
- The dependency tree of the implicit expression is not stored: therefore if a parameter is changed (for example via a .STEP command) then implicit expressions which have been optimized by the option and which depend on this parameter will not be re-evaluated, and results might not be as expected

Eldo will issue an error if it falls into the first two cases above. For the third case, a warning will be issued if some parameter values change at runtime (.step for instance).
- POWNEGO

If an expression exists of the form \(a^{* *} b\left(a^{b}\right)\), with \(a\) being negative and \(b\) being a noninteger value, by default Eldo issues an error. With option pownego, the expression will return 0.0.
- quotrel

This option instructs Eldo to consider double quotes as single quotes. This provides improved compatibility with other simulators. However, character strings are not recognized as such in . PARAM statements. This option is set by default in compat mode (-compat flag or option COMPAT).
- QUOTSTR

This option instructs Eldo to consider double quotes as a parameter string delimiter. This is the default in Eldo, but disabled in compat mode (-compat flag or option COMPAT). Therefore, only use this option in compat mode to identify parameter strings with double quotes.

Note
If both quotrel and quotstr options are specified, the last to be specified is used.
- RMVO

Forces Eldo to connect together the two pins of zero voltage sources if they are not used as an ammeter (that is, if the current flowing through it is never used as a command to control other devices). Connecting the two nodes simplifies the system to be solved.
- SLASHCONT

Allows a single backslash to be used for the continuation of the line. This is automatically set when invoking Eldo with the -compat flag. Example:
```

.option SLASHCONT
R1 1 2 \
3k
R2 1 2 1k

```

R1 will be set to 3 K . When invoking Eldo with the -compat flag, it is possible to disable this option by using . Option nobslashcont.
- STOPONFIRSTERROR=1|2

When set to 1, Eldo will stop parsing the netlist on the first error. This is to prevent the case where Eldo cannot recover correctly from a first error, and would display many subsequent meaningless errors. If the netlist file contains . ALTER statements for multiple simulation runs, Eldo will stop on the first .ALTER that has an error, but continue with the remaining .ALTER statements.
When set to 2, the first error stops the simulation even if the netlist file contains .ALTER statements for multiple simulation runs.
- Strict

Eldo accepts parameter names that contain special characters '!' '|' '<' '>' '?' '\&' (in addition to letters, numbers and characters '_' '\$' '[' ']' '@' 'l' '~' ':' '\#' and '\%'). If option STRICT is set, Eldo will issue an error when using such special characters, and also in the following cases:
- missing ' or \{ around expressions
- double definition of parameter in . PARAM statements
- use of parameter before definition
- double definition of parameters in .MODEL cards
- use of unknown parameter for a model
- double definition of object

Option strict also sets the value of param_before_use to 1 , which imposes that parameters must be defined before being used. See param_before_use for more information.
- SUBALEV

When this option is set with .alter statements in the netlist, then Eldo will substitute all matching lines including those inside subcircuits being substituted. By default (beginning Eldo v6.8) Eldo will substitute only those lines at the top level, to be compatible with other simulators. This option is provided to switch back to the previous behavior for backward compatibility.
- Subflagpar

When this option is set, then analog and eldo are no longer considered as keywords, and these names will be allowed in the subcircuit definition/instantiation of a subcircuit. This option must be specified at the top of the netlist, just after the title line.
By default, it is not possible to create and instantiate a subcircuit named analog or eldo. Therefore, the following design would fail:
```

Title
.subckt analog a b
r1 a b 1
.ends
x1 a b analog
v1 a 0 1
rb b 0 1
.dc
.end

```

However, if option subflagrar is set, then it will be allowed. In such a case, and if the user also wants to set the subcircuit as ANALOG (that is, that the subcircuit should be solved using Newton block iteration techniques), then that flag must be enclosed in brackets, for example:
```

.OPTION SUBFLAGPAR
x1 a b analog (analog)

```

The first occurrence of the parameter analog in the above example stands for the subcircuit name, while the second occurrence, enclosed in brackets, stands for the "high accuracy" flag analog.
- USE_LOCATION_MAP=filename

Specifies the full path and filename to the location map file. Location maps are used to replace prefixes of physical pathnames with environment variables (soft pathnames). If the filename is not found, Eldo displays a warning message.
See "Location Maps" on page 61 for further information.
- USEFIRSTDEF

Forces Eldo to only use the first definition of .mOdel, . SUBCKT, or . PARAM statements. Any further definitions are ignored, to allow the simulation to proceed. By default, when Eldo encounters multiple definitions of .MODEL or .SUBCKт statements Eldo reports an error, and stops the simulation. By default, subsequent definitions of parameters (with .PARAM) do not cause an error, but instead overwrite the previous definition.

Limitation: if this option is used with .ALTER, then new parameter values which appear in the .ALTER section will be ignored, since the first value will always be used.
- USEThREAD=VAL

Activates multi-threading for a single DC or TRAN simulation. Eldo will share computer resources on a multi-processor machine. Eldo will make use of the number of CPUs as specified with this option. The number specified can exceed the number of CPUs available, but this is not recommended. This option is equivalent to the Eldo -usethread val command line flag.

See "Multi-Threading Eldo Simulations" on page 58 for a full description of multithreading in Eldo.
- VOLTAGE_LOOP_SEVERITY=ERROR|WARNING

By default Eldo issues an error (27) when it detects a voltage loop. Use this option to force Eldo to generate a warning instead of an error. Default is Error. See option Loopvo to allow a voltage loop or inductor loop of a zero voltage source, and for more details on voltage loop handling in Eldo. Not supported in compat mode.
- WARN2ERR=VAL

Raises the level of a warning into an error. Eldo will then stop the parsing when this "warning" is reported. Specify as VAL the warning number you want raised. This option must be placed at the beginning of the netlist.

\section*{- XBYNAME}

Map subcircuit pins or nets by name, not by position (default). Allows a subcircuit (X call) to be instantiated using pin/net names of a subcircuit definition (. suвскт command).
When this option is specified, it is possible to mix both syntaxes in the same netlist, Eldo will check for the presence of at least one of the keywords Pin:, PARAM:, NET:, MODEL: or keyword: to select which syntax to be used for each X instance.

See also Subcircuit Instance.

\section*{Simulation Speed, Accuracy and Efficiency Options}

iBefore using the following options it is recommended that the relevant section be consulted in the Speed and Accuracy chapter.
- ABSTOL=VAL

Absolute current accuracy. The default value is vntol \(\times\) Itol. Note AbSI is synonymous to ABSTOL.
- ABSVAR=VAL

Used for timestep control. Sets the maximum voltage change from convergent iteration to iteration (timestep to timestep) for the condition that \(\operatorname{lvLtim}=1\) and \(\operatorname{dVDT=0}\). If the simulator produces a convergent solution that is greater than ABSVAR, the timestep is reduced for the next solution. Default is 0.2 V .
- ADJSTEPTRAN

When this option is set the TPRINT parameter of the .TRAN command is used to calculate minimum and maximum time step values. They are calculated as follows:
\[
\begin{aligned}
& \text { MIN }=\text { TPRINT/10 } \\
& \text { MAX }=\text { MIN(TIME_DURATION/50, TPRINT×RMAX) }
\end{aligned}
\]

Where time_duration is the time duration specified in the .tran command and rmax is the value given by the option ratprint. When ratprint is not specified and adJsteptran is active then ratprint defaults to 2.
- AIDSTP

Forces Eldo to use convergence aid for all . STEP simulations.
When convergence aid is present in the netlist (option GRAMP, . RAMP TRAN, and so on), in combination with . STEP, then the convergence aid instructions are taken into account only for the first step. The assumption being that since subsequent runs use the results of previous . Step simulations to converge, the convergence aid will not be needed. However, sometimes this assumption is not true.
- CAPANW=VAL

Value below which coupling capacitors could be treated by OSR. Defaults to 50 femto Farads, unless option digital is used, in which case it is 1 nF .
- CHGTOL=VAL

Is the absolute tolerance on charge and is used by charge control devices, (for example BIP, DIODE, JFET, BSIM1). Default value is set by ers. This option is only used by the "Gear" algorithm or if option Qtrunc is set.
- DVDT=VAL

Used for timestep control on Newton blocks. When set to 0 , the DVDT algorithm is activated for the condition that lvitim=1. Default is -1 .
- \(\quad \mathbf{E P S}=\mathrm{VAL}\)

Sets the internal simulator accuracy. The default value of EPS depends on the highest voltage levels found in the circuit, based upon the analysis of independent voltage sources. If all voltage levels are below 1.9 V , then the default EPS is set to 1 mV . If any voltage level is higher than 1.9 V , then the default EPS is set to 5 mV . Explicitly specifying an EPS value, . OPtion eps=1e-5 for example, overrides this rule and sets eps to the specified value ( \(1 \mathrm{e}-5\) in this example), regardless of the voltage sources present in the circuit. This voltage source rule is also ignored if EPS is set indirectly via . OPtion tuning=, and the value for eps depends only on the tuning setting, see "Global Tuning of the AccuracyEPS" on page 1070.
Values smaller than \(1.0 \times 10^{-10} \mathrm{~V}\) need to be defined with the unbound parameter (see "UNBOUND" on page 973).
- FASTRLC

For \(\mathrm{R}, \mathrm{L}\) and C elements which have values that vary at run time, a new device evaluation is performed at each iteration to ensure accurate results. When fastric is set, the value used at a given time is not recomputed at each iteration. Instead, the value of previous time step is used. This accelerates the simulation because expressions are not re-evaluated at each time step, at the cost of a lower accuracy. This option only has an effect in TRANSIENT simulation.
- FLUXTOL=VAL

Is the absolute tolerance on flux (for inductors). Default value is set by eps. This option is only used by the "Gear" algorithm or if option gTrunc is set.
- FREQSMP=VAL | \{VAL1, VAL2, . . VALn \}

Forces Eldo to compute a time point at every multiple time interval of 1/FREQSMP, the sampling frequency. Useful when performing a Fourier analysis. Multiple values can be specified as a list in which case Eldo computes timepoints corresponding to all sampled points. For example: a design has two clocks at 2 MHz and 320 kHz . For uniform sampling, time intervals of \(0.5 \mu \mathrm{~s}\) and \(3.125 \mu \mathrm{~s}\) are needed to calculate the necessary exact points (for FFT post processing). Note that if options which impose the sampling frequency are set (for example interpolate \(=0\) on . OPTFOUR), the freqsmp array is reset to a single value. It is possible to assign expression parameters to FREQSMP, for example:
```

.PARAM p1=1k
.OPTION FREQSMP=p1

```
- \(\quad\) FROM_TO=0|1

When enabled (=1), this option will affect the functions min, max and avg of the .meas command. The simulation will stop as soon as all measurements other than min, max and avg which don't have a from= to= parameter are complete. Though the results of these measurements will be not be complete, the simulation will run faster. The default value is 0 .
- \(\quad \mathbf{F T}=\mathrm{VAL}\)

Used for timestep control. When a solution is rejected because of non-convergence (in conjunction with Itl3 and ItL4) the timestep is reduced (multiplied) by the specified fraction \(\mathbf{F r}\). Default value is 0.125 .
- HACC=VAL

Sets the acceleration factor for timestep control. Default value is 2, which means that Eldo will attempt to multiply the current timestep by 2 at most. This time step acceleration strategy is a compromise and is a robust choice providing the best results on average. You are discouraged from changing the value of this option. See "More about time step control" on page 1068 for further details.
- HMIN = VAL

Sets the minimal internal timestep. Default value is 1 ps , which is a value well suited for typical MOS circuits. The default for Switched Capacitor circuits is 2 ns . The default for bipolar circuits is 10 ps. See "More about time step control" on page 1068 for further details.
- HMAX=VAL

Sets the maximum internal timestep. Default hmax value is \(1 / 10\) of the wave period when using SIN and SFFM functions. See also .TRAN TPRINT TSTOP [TSTART [HMAX]] [UIC] in ".TRAN" on page 911. See "More about time step control" on page 1068 for further details.
- hrisefall \(=\) VAL

Forces Eldo to take timesteps not greater than \(d t / v a l\) during transitions as defined by PULSE or PWL signals. VAL is an integer. \(d t\) is the transition time between two time-points corresponding to different values. Default value is 0 . Can be specified by a parameter or expression. For example:
```

.option HRISEFALL = p1
.param p1 = value

```
- INCLIB

Same as the libinc option. Specifies that the full contents of every library are read by Eldo in one pass upon completion of reading the input file. This was the default mechanism in the v5.8 version of Eldo. All the libraries (. LIB) are included without filtering the objects (model, card, or subcircuit) that are not used in the specific netlist.
- ITL1=VAL

Sets a limit on the maximum number of DC iterations. Default value is 100 .
- ITL3=VAL

Used for timestep control. If convergence is reached in less than ITL3 iterations, the next timestep is doubled. Default value is 3.0.
- ITL4=VAL

Used for timestep control. If convergence is not reached within ITL4 iterations, the present timestep is rejected and the next one reduced by fr. Default is 13.0.
- Itle

Equivalent to ITL3 when DC convergence assist is in use. Default value is 5; however this default is 6 in Pseudo-Tran algorithm.
- ITL7

Equivalent to ITL4 when DC convergence assist is in use. Default value is 30; however this default is 20 in Pseudo-Tran algorithm.
- ITL8

This controls the maximum number of iterations allowed for each trial of ramping algorithm (GRAMP, PSTRAN, .RAMP DC). Default is 10000.
- \(\quad\) tTOL=VAL

Controls the current accuracy of the simulator when solving circuits using Newton iterations. Circuit convergence is reached when:
\[
I(i)-I(i-1)|<R E L T O L \times|\max (|I(i)|,|I(i-1)|)|+V N T O L \times I T O L
\]
where \(\boldsymbol{I}(\boldsymbol{i})\) is the current value at voltage iteration \(\boldsymbol{i}\) and \(\boldsymbol{I}(\boldsymbol{i}-1)\) is the previous iteration. Default value is \(1.0 \times 10^{-6} \mathrm{~A} / \mathrm{V}\).
- LIBINC

Same as the inclib option. Specifies that the full contents of every library are read by Eldo in one pass upon completion of reading the input file. This was the default mechanism in the v5.8 version of Eldo. All the libraries (. LIB ) are included without filtering the objects (model, card, or subcircuit) that are not used in the specific netlist.
This mode is also activated in the case of option compat. Option Libinc can also be activated by using the command line flag -libinc at invocation of Eldo.
- LIMNWRMOS=VAL

This option is used to set the value below which MOS resistors are not handled at all. They are not created as objects and not handled in the approximative manner described in the nonwrmos option.

This option is used to collapse intrinsic MOS transistor nodes. With this option, the effect of the parasitic resistors upon the channel current is still taken into account, although not as accurately as when the nodes are explicitly created. Particularly, some of the overlap capacitances in the MOS model become connected to the external drain/source, whereas they really are connected to the internal nodes. This may change results slightly.
- LVLTim=VAL

Sets the simulator Time Step Control algorithm. See also "Time Step Control—Algorithm Selection with the LVLTIM Option" on page 1066.
- MAXNODES=VAL

To optimize memory allocation when simulating large circuits, the maximum number of circuit nodes may be specified. We recommend use of a value larger than the number of nodes in the circuit, to prevent memory re-allocation procedures.
- MAXSTEP=VAL

Controls the maximum number of runs allowed for a . STEP simulation. Default value is 25000. An error message is generated when more runs are requested as follows (example):
```

ERROR 1580: COMMAND .STEP TGIG : suspicious number of runs: 226250001.

+ The maximum allowed value can be set by .OPTION MAXSTEP=val.
+ Current value is 25000.

```
- MAXTRAN=VAL

Specifies the maximum number of circuit components in order to optimize memory allocation when simulating large circuits. We recommend a value larger than the number of components in the circuit, to prevent memory re-allocation procedures.
- MAXV \(=\mathrm{VAL}\)

Sets maximum voltage values for which Eldo searches for the DC operating point of a circuit. The options vmin and vmax also set bounds on DC operating point voltages, but maxv overrides vmax. Default is \(1.0 \times 10^{13} \mathrm{~V}\). Thus maxv must be specified if there are operating points greater than \(1.0 \times 10^{13} \mathrm{~V}\) in the circuit.
- NETSIZE=VAL

Provides a rough guess about the size of the Newton matrix.
- NGTOL=VAL

Is the absolute tolerance on voltage. Default value is set by ers. This option is only used by the "Gear" algorithm or if option etrunc is set.
- NMAXSIZE=VAL

Sets the maximum number of nodes that can be contained in a single Newton block. Default value is \(6.0 \times 10^{4}\). However, if the newton option is explicitly specified, it has priority, and NMAXSIZE defaults to \(5.0 \times 10^{6}\). This is in order for very large MOS circuits, containing over 60,000 nodes, to be simulated by default with OSR.
The nmaxsize option works in the following way:
Eldo attempts to partition:
If nb_nodes < NMAXSIZE, Eldo can attempt only one block, or it will attempt several blocks. This depends upon ePS and the option BLOCK=<> specification.
Else, Eldo will attempt several blocks.
However, in the process of creating blocks, nmaxsize is not checked. The matrix grows depending on the connectivity, and the matrix size may exceed nmaxsize. The growth of the matrix cannot be stopped at that step, since the simulation would probably not work if we decide to split the matrix at those points where Eldo sees potential important feedback.

Once the blocks are completed, Eldo will attempt to concatenate blocks in case it sees feedback between blocks. However, it will not concatenate blocks if the sum of their size exceeds nMAxsIze.
- NOCONVASSIST

Disables the automatic convergence aid mechanisms. This is specified to avoid other algorithms when non-convergence occurs. In this case Eldo will try the first algorithm and if there is a non-convergence problem the simulation is stopped and Eldo returns the list of nodes.
- NODCPOWNEG

The power dissipation returned at DC operating point takes into account the power of all independent V and I sources (beginning v6.8). Specify this option for backward compatibility; only those V and I sources which generate power are considered (that is, those for which \(\mathrm{I} \times \mathrm{V}\) are negative), which corresponds to the majority of the cases.
- nolat

Suppresses latency optimizations.
- NONWRMOS

This option is used to collapse intrinsic MOS transistor nodes. With this option, the effect of the parasitic resistors upon the channel current is still taken into account, although not as accurately as when the nodes are explicitly created. Particularly, some of the overlap capacitances in the MOS model become connected to the external drain/source, whereas they really are connected to the internal nodes. This may change results slightly.
When this option is active, there might be situations where DC cannot be found. If this happens, remove the option. Even when DC is found, if the netlist contains some MOS devices with forward biased bulk-source and bulk-drain junctions, Eldo will detect such situations during DC convergence, and will resimulate with the option disabled.

See also "Collapse the intrinsic MOS transistor nodes" on page 1077 for further information.
- nogtrunc

Disables the charge-based Local Truncation Error algorithm. See option qTrunc.
- NOSWITCH

Forces Eldo to ignore the switch keyword specified as part of a subcircuit instance in the netlist.
- PCS=0|1|2|3
(Periodic Circuit Speedup) Used to increase the simulation speed for circuits with periodic or nearly periodic nature. PLLs in near-lock state belong to this category. The amount of speedup depends on the design nature. The speedup will be more significant with relatively large circuits. With circuits showing no periodicity at all, the option will not usually provide any speedup and may even slow down the simulation. Periodic Circuit Speedup is invoked by setting PCS=1|2 for BSIM3v3 models only (pCS=1|2 represent two possible speed
optimization methods, \(\mathrm{PCS}=1\) is more recommended) or \(\mathrm{PCS}=3\) for BSIM4 and BSIM3v3 models (with same speed optimization as PCs=1). Default is 0 . This option only supports the BSIM3v3 and BSIM4 models.

\section*{Note}

BSIM4, unlike BSIM3, has many parasitic configurations: gate resistors, body resistors network, bias dependent access resistors, and so on. These parasitic configurations are controlled by a set of instance and model parameters (Rdsmod, Rbodymod and Rgatemod). As the complexity of the parasitic configuration around the core model increases, the gain expected by the PCS decreases.

\section*{Caution}

Use of the PCS option in the case of non-periodic conditions may even slowdown the simulation a little, which is why this option is not set by default. In this case, try using the PCS option in conjunction with the .OPTPWL or .OPTWIND commands to specify the time after which to turn on PCS.
- PCSSIZE=VAL

This option is used to specify the memory size (in MB) to be used by the PCS algorithm. The default value is 128 . In many cases increasing this value will enhance the speedup achieved by the PCS option. However this value should not exceed the available physical memory to prevent memory allocation problems and excessive slowdown due to disk access.
- PCSPERIOD=VAL

This option can be used to specify a guess for the period of the circuit. When provided, this guess can be used to enhance the speedup achieved by the PCS option.
- \(\quad\) PIVCHECK=1|2

Used in the LU-Factorization algorithm in order to check the magnitude of terms in the matrix. Matrix manipulations can lead to very large numbers which may overshoot the machine's capacity to store a real value resulting in an Error Code 6. When this option is set, Eldo performs preliminary checks on matrix terms to prevent such an error. As it is time consuming it is not set by default and should not be set unless requested by Eldo. Two levels of safety are provided to prevent such errors in the matrix resolution, each one slower than the default and level 2 slower than level 1. pivcheck=1 should be specified first and if this still fails to resolve the issue then Eldo will inform you to set PIVCHECK=2.
- PIVREL

Used in the LU-Factorization algorithm in order to find a compromise between the value of a pivot (the larger a pivot the better it is from a numerical point of view) and the fill in of the matrix (the less fill-in the more efficient future matrix manipulations will be). Default value is \(1.0 \mathrm{e}-3\). You are invited to change this value whenever Eldo informs that the matrix is singular.
- PIVTOL

Is the absolute minimum value that can be accepted in the matrix to be a pivot for the LUFactorization algorithm. Default is \(1.0 \mathrm{e}-16\). You are invited to change this value whenever Eldo informs that the matrix is singular.
- PSOSC=VAL

Allows control of the maximum number of oscillations that can occur when using a DC pseudo-transient algorithm during DC. This is to avoid a never-ending loop in cases where the amplitude of the oscillations does not decrease. Default value is 10 . If the user knows that the oscillations amplitude decreases after \(n\) periods, \(\mathbf{p s o s c}=\mathrm{n}\) can be specified to increase the Eldo limit.
- QTRUNC

Forces Eldo to use a Local Truncation Error algorithm as in a SPICE like simulator. By default, the Eldo timestep is calculated from voltages using a predictor-corrector algorithm. This algorithm is suitable for IC circuits, however, for PCB-like circuits, it is preferable to use a Local Truncation Error timestep algorithm calculated from charges (and flux) as in SPICE like simulators. otrunc is automatically switched on if the circuit contains large current sources of above 1 A , magnetic models or large power supplies. The option nogtrunc may be used to disable this algorithm. The Local Truncation Error algorithm, when working on charges or fluxes, uses the same control variables as the GEAR option, (that is, reltrunc, cghtol, fluxtol and ngtol).
- RATPRINT=VAL

If specified, then delmax is computed as:
\[
\min \left(\frac{T S T O P}{50}, R A T P R I N T \times T P R I N T\right)
\]

If not specified, then the default algorithm is used and delmax is not computed from .tran specifications.
- RELTOL=VAL

Controls both the timestep size and the accuracy of Newton and/or IEM iterations. For voltages, convergence of iterations is reached when:
\[
|V(i)-V(i-1)|<R E L T O L \times|\max (|V(i)|,|V(i-1)|)|+V N T O L
\]
where \(\boldsymbol{V}(\boldsymbol{i})\) is the voltage value at current iteration \(\boldsymbol{i}\) and \(\boldsymbol{V}(\boldsymbol{i}-1)\) is the previous iteration. For currents, circuit convergence is reached when:
\[
|I(i)-I(i-1)|<R E L T O L \times \max (|I(i)|,|I(i-1)|)+V N T O L \cdot I T O L
\]
where \(\boldsymbol{I}(\boldsymbol{i})\) is the current value at voltage iteration \(\boldsymbol{i}\) and \(\boldsymbol{I}(\boldsymbol{i}-1)\) is the previous iteration. Default value is \(1.0 \times 10^{-3}\).
reltol also controls the time step size via the Local Truncation Error (LTE). This feature was added for compatibility with SPICE.
- RELTRUNC=VAL

Is the relative tolerance on the chgtol, ngtol and fluxtol parameters above. Default value is set by eps.
- relvar

Used for timestep control. Sets the relative voltage change for the condition that lvitim=1 and \(\operatorname{DVDr}=0\). If the nodal voltage at the present time point exceeds the nodal voltage at the last time point by relvar, the next timestep is reduced and a new solution is calculated. Default is 0.15 .
- SAMPLE=tval

May be used to speed-up simulation of sampled circuits containing OPA macromodels and/or switch macromodels. The simulation timestep is set to the value tval specified. Eldo then computes additional intermediate timesteps (that is, at tval \(/ 2,3 \mathrm{tval} / 2,5 \mathrm{tval} / 2\), ...), in order to compute values when the signals should have reached their steady state values. The SAMPLE option also causes simplified OPA and switch macromodels to be used. The slew-rate of the simplified OPA macromodel is assumed to be infinite, and the simplified switch resistor value is either RON or ROFF, with no linear transition in-between.
- SPLITC[=val]

Simulation of floating capacitors (for example, those derived from extraction) can be optimized by changing the value of this option. This will force Eldo to split a capacitor object into two capacitors, each connected between ground and one node of the original capacitor. This leads to faster, but less accurate simulations. This splitting occurs for capacitors with values greater than val. Default is 50 fF ( 1 nF if digital option is specified).
This option is also used with ADiT in a slightly different way. A floating capacitor affects the partitioning between Eldo and ADiT solvers, if it connects two blocks that are assigned to the two different engines. Using this option allows the defined partitioning if capacitor value is less than val. In ADiT, val defaults to 1 fF .

When splitc is specified with a value, the same value is used as a threshold for both the capacitor splitting in Eldo and the ADiT partitioning.
When splitc is specified without a value, then all the default values are used (including for ADiT partitioning).
When splitc is not specified at all, then no splitting of capacitors occurs in Eldo (floating capacitors remain floating), however the default 1 fF value is used as a threshold for ADiT partitioning.
- STARTSMP=VAL

Used in conjunction with freqsmp. The freqsmp command will be active after startsmp.
- STEP=VAL

Imposes a fixed timestep to be used by Eldo as defined by the VAL value. By default, Eldo uses a varying timestep.

\title{
Note \\ . OPTION STEP could produce incorrect results near breakpoints when used with the IEM method. This can occur if the Step value is set greater than the rise and fall times of the circuit.
}
- TIMESMP=VAL \(\mid\) VAL1, VAL2 2 . . .VALn \}

Forces Eldo to compute a time point at every multiple time interval of timesmp, the sampling time interval. Equivalent to \(1.0 /\) Fregsmp. Useful when performing a Fourier analysis. Multiple values can be specified as a list in which case Eldo computes timepoints corresponding to all sampled points. For example: a design has two clocks at 2 MHz and 320 kHz . For uniform sampling, time sampling of \(0.5 \mu \mathrm{~s}\) and \(3.125 \mu \mathrm{~s}\) are needed to calculate the necessary exact points (for FFT post processing). Note that if options which impose the sampling frequency are set (for example interpolate \(=0\) on . OPTFOUR), the timesmp array is reset to a single value.
- TRTOL=VAL

Used for timestep control. Serves as a multiplier of the internal timestep generated by the Local Truncation Error timestep algorithm (lvitim=2). It is a factor that estimates the amount of error introduced in truncating a series used in the algorithm. This error is a reflection of what the minimum value of the timestep should be to reduce simulation time and maintain accuracy. The larger trtol is, the larger the timestep will be. Default value is 7.0 .
- TUNING=[FAST |STANDARD \(\mid\) ACCURATE \(\mid\) VHIGH \(]\) [TUNING=BACKANNOTATE]

Selects the default mode of operation with regards to precision and speed. This tuning option acts as a macro-controller of Eldo: it enables the selection of algorithm and parameter settings via eps. Any given parameter can be explicitly imposed, which will supersede the value related to the tuning setting. Note: the order of the option is important, the tuning type must be set first and then you can adjust any parameter with specific values. This option is equivalent to the -tuning command-line flag of Eldo. The -tuning flag overrides any tuning option settings inside the netlist.
fast keeps Newton as the default algorithm, unless options OSR or IEM are explicitly imposed. fast gives milder values to some tolerance parameters (itol, vntol and abstol, but not eps) in order to have faster but still reliable simulation, even if slightly less accurate. Well suited to efficiently simulate large analog or mixed circuits.
standard (this is the default) causes eps to be set to \(5.0 \mathrm{e}-3\) and activates the newton option unless options OSR or IEM are explicitly imposed.
accurate causes eps to be set to \(1.0 \mathrm{e}-6\) and activates the newton option unless options OSR or IEM are explicitly imposed.
vhigh causes eps to be set to \(1.0 \mathrm{e}-8\) and activates the newton option unless options OSR or IEM are explicitly imposed.
backannotate enables an improved Eldo solver to be used for handling backannotated netlists with many parasitic elements. Backannotate can provide significant capacity and speed improvements (up to \(10 \times\) ) for DC, TRAN and all RF analyses for circuits which contain parasitic elements. It is most efficient when the parasitics are defined in DSPF format in a separate file. This can be specified in addition to one of the other keywords above. When specified alone, Eldo will automatically set
tuning=standard. The classical tuning values are for Eldo accuracy and speed, and backannotate is for speed with parasitics usage. The tuning option only accepts one argument at a time, so the option has to be repeated when combining arguments, for example:

TUNING=ACCURATE TUNING=BACKANNOTATE
For AC and transient noise (.noisetran) analyses the backannotate algorithm is deactivated due to some inaccuracies in results. It can be forced by specifying TUNING=AC_BACKANNOTATE, however results cannot be guaranteed.
For greater flexibility, the backannotate algorithm can be activated or deactivated for a particular analysis by using one or several of the following options:
```

TUNING=DC_BACKANNOTATE (activates the solver for DC analysis)
TUNING=AC_BACKANNOTATE (activates the solver for AC analysis)
TUNING=TRAN_BACKANNOTATE (activates the solver for Transient analysis)
TUNING=SST_BACKANNOTATE (activates the solver for all RF analyses)
TUNING=NODC_BACKANNOTATE (deactivates the solver for DC analysis)
TUNING=NOAC_BACKANNOTATE (deactivates the solver for AC analysis)
TUNING=NOTRAN_BACKANNOTATE (deactivates the solver for Transient analysis)
TUNING=NOSST_BACKANNOTATE (deactivates the solver for all analyses)

```

\section*{Note}
tuning can also be specified using the time window .OPTPWL or .OPTWIND
commands to apply or disable it during or outside some time intervals. The
backannotate tuning options do not support these commands.
- UNBOUND

Enables an EPS value smaller than \(1.0 \times 10^{-10}\) to be specified. This option may be used for special applications that use low currents. Care must be taken, however, as problems with convergence may occur due to accumulation of round-off errors.
- \(\mathbf{V M I N}=\mathrm{x} 1\),

VMAX \(=x 2\)
Sets the minimum and maximum voltage values for which Eldo searches for the DC
operating point of a circuit. Power supply levels are very often parametrized, and the values of vmin and vmax typically depend on the power supply. Therefore vmin and vmax can have their values specified by parameters. For example:
```

.param foo = 1.0
.option vmin = '-10*foo' vmax = '10.0*foo'

```
- VNTOL=VAL

Controls the voltage accuracy of the simulator when solving circuits using Newton Raphson techniques. Circuit convergence is reached when:
\[
(|V(i)-V(i-1)|<R E L T O L \times|\max (|V(i)|,|V(i-1)|)|+V N T O L)
\]
where \(\boldsymbol{V}(\boldsymbol{i})\) is the voltage value at current iteration \(\boldsymbol{i}\) and \(\boldsymbol{V}(\boldsymbol{i}-1)\) is the previous iteration. Default value is \(1 \mu \mathrm{~V}\). Note AbSv is synonymous to vntol.
- WDB_IDELTA=VAL

This option is used to define the delta I for use with all current plots, using this option will reduce the size of the wave database. Only for use with the JWDB (.wdb) output format. Default value is 0.0.
- wDB_VDELTA=VAL

This option is used to define the delta \(V\) for use with all voltage plots, using this option will reduce the size of the wave database. Only for use with the JWDB (.wdb) output format. Default value is 0.0.
- WDB_NOSYNCHRO \(=0 \mid 1\)

When set to 1 this option forces Eldo to send unsynchronized waves to the database using default VDELTA and IDELTA values. This will reduce the size of the wave database. Only for use with the JWDB (.wdb) output format. Default value is 0 .
- \(\quad \mathbf{X A}=V A L\)

Diffusion length for MOS S/D calculation. Default value is \(6 \mu \mathrm{~m}\).
\[
\begin{aligned}
& \text { Weff }=W-D W-2 \times k l \\
& \text { ADeff }=\text { Wef } f \times x a \\
& \text { ASeff }=W e f f \times x a \\
& \text { PDeff }=\text { Weff }+2 \times x a \\
& \text { PSeff }=W e f f+2 \times x a
\end{aligned}
\]

\section*{Miscellaneous Simulation Control Options}
- AMMETER

Prevents Eldo from eliminating zero voltage sources which are frequently used as current probes.
- AUTOSTOP=0|1|2

This option can be specified to reduce the simulation time. It stops a Transient simulation, when the Transient Extraction Language functions trd, trise, trall, tcross are used. It can also be used with the General Extraction Language functions: xdown, xUP, yVAL, xthres. For any other functions present in the netlist, the autostop specification will be ignored.

\section*{AUTOSTOP=0}

Deactivates autostop if necessary. Default.

\section*{AUTOSTOP=1}

Causes Eldo to stop the simulation when all extracted waveform information (. EXTRACT/. MEAS) has been measured.

AUTOSTOP=2
Used in multi-step simulations. Causes Eldo to stop when all sweep measurements are completed.
- AUTOSTOPMODULO=VAL

This option is for use with the AUtostor option. It only has an effect in TRANSIENT analysis. The evaluation of MEAS/EXTRACT will be performed only at every Autostopmodulo steps. This can be used to overcome the simulation slow down sometimes caused by setting autostor, especially when the time spent to evaluate the MEAS/EXTRACT is large compared to the time taken to solve for the circuit. Default is 0 , meaning that evaluation is performed at each step.
- CARLO_GAUSS

Option for Gaussian distribution in Monte Carlo analysis. This option has two effects:
- All цот/Dev statements having no distribution type specification, will be assumed to have a Gaussian distribution, that is, default is:

LOT/GAUSS or DEV/GAUSS
Example:
```

VTO = 1 LOT/UNIFORM = 20%
EOX = 10n LOT = 12%
.OPTION CARLO_GAUSS

```

In this example the distribution on eox will be Gaussian, while the distribution on vTO will remain uniform.
- The envelope returned in the binary output files (or in the .PRINT commands) is computed from the standard deviation and do not correspond anymore to (MIN, MAx) of the waveform.
- CPTIME=VAL

Stops the simulation if the CPU time exceeds VAL seconds. Message is displayed in the .chi file as well as being sent to the screen.
- DEFAULTFALLTIME=VAL

Transition time in seconds for signal changing from high to low state. Used as a default by test vector files, see ".TVINCLUDE" on page 918. Default value is 1e-10.
- DEFAULTRISETIME=VAL

Transition time in seconds for signal changing from low to high state. Used as a default by test vector files, see ".TVINCLUDE" on page 918. Default value is \(1 \mathrm{e}-10\).
- DEFPTNOM

Allows a parameter to be defined with the name tnом. In such a case, this value will be used inside parameter expressions instead of the default тлом or the value set using option TNOM=val. This option must be specified at the top of the netlist. The temperature value used by the Eldo model evaluator is always that set with option tnom=val.

In the following example, the voltage source will use the value specified by tnom in the . PARAM command; without option Defrtnom the default tnom value would be used:
```

.option defptnom
...
.param tnom=50
v1 1 0 tnom

```
- DSCGLOB=X \(\mathbf{~ G L O B A L}\)
x
This is the default. Nodes which appear in subcircuit definitions have priority over the nodes defined with . Global statements. See ".GLOBAL" on page 676. This option must be specified at the very beginning of the netlist.

\section*{GLOBAL}

When specified, nodes defined with . Global statements have priority over the nodes which appear in subcircuit definitions. See ".GLOBAL" on page 676. This option must be specified at the very beginning of the netlist.
See "DSCGLOB Option Example" on page 903.
Note
When Eldo finds a subcircuit definition which uses global nodes, Eldo issues a warning to inform you how the situation is handled.
- DSPF_LEVEL=C|RC|RCC

Defines the level of parasitics to use from a specified DSPF file. The option will use part of the information stored in the RC extracted DSPF file specified by c, RC or RCC.

DSPF_LEVEL=C
Where c is the intrinsic and coupling capacitance. The pre-layout nets will obtain a grounded capacitance, as specified in the DSPF file in the line *|net.

\section*{DSPF_LEVEL=RC}

Where RC is the distributed RC elements. The ideal pre-layout nodes will be replaced with RC elements. Also the coupling capacitance between wires/layers is ignored, that is any capacitor that is not grounded (floating) will be ignored.

DSPF_LEVEL=RCC
Where RCC is both intrinsic and coupling capacitance and distributed RC elements. It is assumed that the DSPF file has been extracted with all RCC information.

\section*{Note}

This option can also be specified by the level parameter in the .DSPF_INCLUDE command, see ".DSPF_INCLUDE" on page 617. If specified in the command it will overwrite this option.
- FLOATGATECHECK

If a node is connected to at least one MOS gate, and is not connected to anything else but MOS gates, capacitors, or a reverse-biased diode, it is considered as a floating gate.

This option enables Eldo to issue a warning when a floating gate is detected and resume the simulation. Eldo will not consider reverse-biased diodes as active elements when checking for floating gates. Reverse-bias conditions are detected as follows:
- If the node is connected to the first pin of a diode, then the other pin must be connected to the positive node of a power supply to be considered as reverse-bias.
- If the node is connected to the second pin of a diode, then the other pin must be connected to either ground or the negative pin of a power supply to be considered as reverse-bias.

This option can be used in conjunction with the options FLOATGATERR and FLOATGATEO.
- FLOATGATERR

Enables Eldo to stop the current process and generate an error when floating gates are detected. It can be used in conjunction with the option FLOATGATECHECK.
- floatgateo

This option will force detected floating gates to 0 . It can be useful to change the topology of a circuit and achieve better convergence. It can be used in conjunction with the option FLOATGATECHECK.
- FALL_time=VAL

Transition time in seconds for signal changing from high to low state. Used by the interactive LOW command. Default value is 1 ns .
- RISE_TIME=VAL

Transition time in seconds for signal changing from low to high state. Used by the interactive HIGH command. Default value is 1 ns .
- highvoltage=Val

Sets the upper bus signal voltage level. Default is 5V. This option (and lowvoltage) is only used by the . TVINCLUDE command and by interactive commands.
- Lowvoltage=val

Sets the lower bus signal voltage level. Default is 0V. This option (and highvoltage) is only used by the . TVInclude command and by interactive commands.
- LOWVTH=VTH1

See below. Default value is 2.4 V . This option (and нієнvтн) is only used by the .tvinclude command.
- highvth=Vth2

Default value is 2.6 V . This option (and Lowvth) is only used by the .tVinclude command.

The vth parameters are required by Eldo to compute the hex (or Dec, ост, or bin) value on the bus from the analog value inside Eldo. Then, it compares this value with the value expected and displays the error if they are not the same.
When only vth1 is given:
If value < vth1 then logic state 0 .
If value > vth1 then logic state 1 .
HighVth=vth2 is used to plot the indeterminate value as shown below:
If value \(<\) vth1 then logic state 0 .
If vth1 < value < vth2 then state X.
If value \(>\) vth2 then logic state 1 .

- Interp

Causes Eldo to generate data in the binary waveform output file in the same way it does in the .chi file. Therefore, rather than producing data as it is calculated it will only produce points at each timestep specified in the analysis. Example:
.TRAN 1n 10n .OPTION INTERP

This will generate data in the binary output file every 1 ns. If INTERP is not specified, then Eldo will dump points that it has actually computed.
- ICDC and ICDEv

By default, Eldo behaves like Spice 2 g 6 regarding . Ic commands and ic parameters specified on devices: . Ic commands are taken into account only for DC done before Transient analysis, or when .TRAN ... UIC is specified. However, IC parameter specifications on devices are taken into account only in the case of .TRAN ... UIC.
- ICDC

In this case, . Ic commands (and Ic parameter specifications on devices when option ICDEV specified) will be taken into account for any DC analysis.
- ICDEV

In this case, Ic parameters specified on devices and .IC commands will be handled the same way.
- LICN

By default, the first initial condition (. Ic) specification has precedence over subsequent IC specifications. Setting LICN, the last IC specification will have precedence. This option is automatically set if compat mode is used.

The same remark applies to .nodeset, or .guess. Setting Licn, the last .nodeset (or .guess) specification will have precedence over the previous .nodeset (or . Guess) specifications. See ".IC" on page 682, ".GUESS" on page 677, and ".NODESET" on page 743.

\section*{Note}

Whether or not LICN is specified, .nodeset always has precedence over . Guess, and whenever . Ic commands are active (that is, during the DC which is done prior to TRANSIENT simulation, or whenever option ICDC is active), then . IC has precedence over .nodeset.
- LVS_IGNORE_VARIABLE="names"

Specifies a list of LVS (Layout Versus Schematic) variables that Eldo will ignore for MOS, BJT, diode, and JFET devices. Specify the variables in a list separated by commas. For example:
```

.OPTION IGNORE_LVS_VARIABLE = X, Y, D

```

Eldo ignores the \(\$ \mathrm{X}, \$ \mathrm{Y}\), and \(\$ \mathrm{D}\) LVS variables and associated values.
- M53

Specifies the ruling surrounding the M factor should be as it was for versions of Eldo before and including v5.3. Example:
```

.SUBCKT mysubckt in out m=5
r1 in 1 1k m='2*m'
r2 1 out 1k
.ends
X1 in out mysubckt m=3

```

The above example used to work for previous versions of Eldo (Eldo would simulate as if there were six x1.r1 devices in parallel, but only one x1.r2.). For Eldo version v5.4 and higher, the rule regarding the \(m\) factor changed. The \(m\) value can appear on the \(X\) instance or on the device. The \(m\) value cannot appear anymore on the Right-Hand-Side of the expression. In the example above, Eldo will issue an error. To avoid this error, it is therefore mandatory to replace the \(m\) parameter in any expression, by another parameter name. In the example below, no confusion is possible:
```

.SUBCKT mysubckt in out mr=5
r1 in 1 1k m='2*mr'
r2 1 out 1k
.ends
X1 in out mysubckt mr=3

```

Here, the user will still have six devices of \(\mathrm{x} 1 . \mathrm{r} 1\), and only one of \(\mathrm{x} 1 . \mathrm{r} 2\). Of course, if the user put the \(m\) factor on the subcircuit instantiation:
```

X1 in out mysubckt m=3 mr=3

```

Here, 18 devices of \(\mathrm{x} 1 . \mathrm{r} 1\), and three devices of \(\mathrm{x} 1 . \mathrm{r} 2\) will be emulated.
For backward compatibility, you can invoke Eldo with the -m53 flag, or use option m53 (to be placed at the beginning of the .cir file, just after the title).
- MC_IGNORE_BINNING

Disables automatic selection of the binning parameters at run time; the model selected at the nominal run will then be used for the whole MC process. See Define Monte Carlo Parameters.
- ммSmooth

Use this option to make \(\mathbf{M I N} / \mathbf{M A X} / \mathbf{A B S} / \mathbf{S G N} / \mathbf{s I G N}\) operators derivable, to avoid convergence problems. The \(\mathbf{m I n} / \mathbf{m A X} / \mathbf{A B S} / \mathbf{S G N} / \mathbf{s I G N}\) operators, when used in bias-dependent expression (such as in \(R(V)\) ), can cause non-convergence due to these operators making the function non-derivable.

With option ммSмоотн:
\[
\begin{array}{ll}
\operatorname{MIN}(a, b)=a-0.5 \times\left((a-b)+\sqrt{(a-b)^{2}+e p s}\right) \\
\operatorname{MAX}(a, b)=b+0.5 \times\left((a-b)+\sqrt{(a-b)^{2}+e p s}\right) \\
A B S(v a l)=\sqrt{v a l^{2}+e p s} & \\
\operatorname{SIGN}(v a l)=-1 & \text { when } v a l<-e p s \\
\operatorname{SIGN}(v a l)=\sin \left(\frac{\pi}{2} \times \frac{v a l}{e p s}\right) & \text { when } e p s<v a l<e p s \\
\operatorname{SIGN}(v a l)=1 & \text { when } v a l>e p s
\end{array}
\]
eps is the smoothing coefficient, which can be set with option ммSmоотнерs=val. Default is \(1.0 \mathrm{e}-3\).

Notes:
- setting mMSMOOtheps=val automatically activates min/MAX/ABS/SGN/SIGN operator smoothing, that is, it emulates the specification of option ммSмоотн
- ммямоотн works only on bias-dependant expressions used on devices, it has no effect on other types of expressions (.DEFWAVE for example)
- Smooth min/max/Abs/sGn/sign operators also exist as built-in operators: SMMIN (a,b,eps), SMMAX(a,b,eps), SMABS (val,eps), SMSGN(val,eps), and SMSIGN (val,eps) ; see "Arithmetic Functions and Operators" on page 78
- MMSMOOTHEPS

Specifies the smoothing coefficient, eps, used to make min/mAx/ABS/SGN/SIGN operators derivable. Default is \(1.0 \mathrm{e}-3\). Setting mмsmoothers=val automatically activates \(\mathbf{M I N} / \mathbf{M A X} / \mathbf{A B S} / \mathbf{S G N} / \mathbf{S I G N}\) operator smoothing, that is, it emulates the specification of option ммямоотн. See also option MMSMOOTH above.
- noicnode

Causes Eldo to ignore any . Ic commands.
- NOLICN

Causes the first initial condition (. Ic) specification to have precedence over subsequent IC specifications. If running Eldo in compat mode, option LICN is automatically set causing the last initial condition (.IC) specification to have precedence over previous IC specifications. Use option Nolics to disable this behavior for backward compatibility (prev6.9).
- noltedisc

Bypass LTE checks on those devices where convergence problems or slow simulation are observed. When using operators such as CEIL, ROUND, FLOOR on bias dependant expressions, for example \(E 12\) value \(=\{\operatorname{round}(\mathrm{v}(\mathrm{in})+2\}\), convergence problems may be caused because the functions are not continuous. When Eldo encounters such objects, it will generate a warning about these possible convergence problems, and will invite the user to use this option.
- NOMEMSTP

Setting this option means Eldo will not use the results of the previous STEP run as an initial guess for the next one. By default, without this option, the second run in . STEP uses the result of the previous STEP as an initial guess.
- novatopochk

Bypass topology checks for Verilog-A module instances. Beware that voltage loop and DC path to ground dection procedures for the whole circuit may be affected by this option if there are Verilog-A instances.
- PARAMOPT_NOINITIAL

This option can be used for the Eldo optimizer. Allows the initial value parameter of the .PARAMOPT syntax to be omitted. The value already available in the netlist through the normal . PARAM specification will instead be used.
- PODEV

This option is used to specify dev variation for a declared Monte Carlo analysis distribution parameter when the parameter is used as part of either a model or instance parameter. By default Lот variation is used for model parameters and DEv is used for instance parameters. In Eldo versions prior to v6.3_2 DEv variation was the default for both model and instance parameters.
- RANDMC

Reset the MC randomly. The sequence of random numbers differs from one run to the next.
- RGND=val

When this option is set a resistance is connected between a node and ground for nodes that have no DC path to ground (warning message 118), for example a node to which only capacitors are connected. This allows the simulation to proceed instead of producing errors. It differs from option RGNDI which is used only for dangling nodes connected to a current source. This option connects a resistance of val and allows the simulation to proceed.
- RGNDI=val

When this option is set a resistance is connected between the dangling nodes of independent current sources and ground. Normally if Eldo detects a dangling node on a current source an error is issued and the simulation stops. This option connects a resistance of val and allows the simulation to proceed.
- SIGTAIL=VAL

This option can be used in Monte Carlo analysis. The value represents the relative maximum extension of the Gaussian tail when Gaussian distribution is used. The default is 4. Example:
```

.param p1=1 lot/gauss=0.1
.option sigtail=6

```

Here, p1 values will be in the range \([0.4,1.6]\) (which is equivalent to nominal- 0.6 , nominal+0.6). If sigtail is not specified, p1 values will be in the range [0.6, 1.4] (equivalent to nominal-0.4, nominal+0.4).
- Statistical =ol1

Specifies whether any statistical variation due to .MC, . WCASE, or .DCMISMATCH can be applied to X instances, device declarations, or . Subckt definitions. If statistical is 0 , the selected devices will keep their nominal values. If statistical is 1 , the selected devices have statistical variation applied. Default is 1 .
- TEMP_UNIT=KELVIN|CELSIUS

Specifies the unit used for temperature values inside the netlist. Default is Celsius. This has an effect on commands . STEP TEMP <t1> <t2> and. TEMP <t1> and on the unit used to print temperature values in the outputs: simulation information, .EXTRACT results, in .aex file, and so on.
- TNOM=VAL

Sets the model temperature, that is, the temperature defined in the model. Default is \(27^{\circ} \mathrm{C}\).
- TPIEEE

For each port for which noisetemp is not specified, then the value 16.85 will be used rather than the temperature of the circuit. See "NOISETEMP" on page 315 and "NOISETEMP" on page 315 in the V\&I Sources.
- Ulogic

Causes a current source/RC combination to be used on the output of Eldo logical primitives AND, NAND, and so on. By default, the output of Eldo logic gates acts as a pure voltage source, making simulation very fast, but not allowing easy arbitration of signals when logical outputs are connected together. By using ULOGIC, depending on the values of driving resistance used, such conflicts may be resolved. Note that in this mode of operation, simulation speed is slightly slower than the default voltage source method.

See "Digital Model Definition" on page 449 for details of output resistor and propagation delay model parameters.
- ZOOMTIME=VAL

The hold times of pwl, pulse and pattern sources are extended by multiplying them by a factor VAL. Source rise and fall times remain unchanged.

\section*{Model Control Options}
- ACDerfunc

Derivative of function selector. For AC analysis only. For voltage or current dependent R/L/C devices, the derivatives of the value with respect to the voltage are dumped in the matrix by default. By default this option is set (prior to Eldo v6.8 it was not). This can be disabled by globally setting NOACDERFUNC (see "NOACDERFUNC" on page 989), forcing Eldo to not dump these values in the matrix. Device objects can be individually set with the acderfunc local parameter. The specification on the device overrides any global setting by options acderfunc or noacderfunc.
- ACM

Usually acm is just a parameter which is an alias to Ardev; that is, it overwrites the values of alev and rlev. However, if you specify acm in the netlist, then acm has a much more effective role. This option is automatically set if compat mode is used.

Please refer to .OPTION ACM of the Eldo Device Equations Manual.
- ASPEC

Controls use of sCale and scalm values with the models. When this option is specified, the following conditions are set:
```

.OPTION SCALE = 1U
.OPTION SCALM = 1U
.OPTION WL

```

This option is intended for use with ASPEC MOSFET models (Eldo level 16), but also impacts other models because the options set are global.
- BSIM3VER=VAL

There are several versions of the BSIM3v3 model. See "Berkeley SPICE BSIM3v3 Model (Eldo Level 53)" on page 273. This option is an alternative to the model parameter VER for setting the version to use. By default, BSIM3v3.2.4 (ver=3.24) is selected.
- DEFAD=VAL

Sets the default value for MOS drain diffusion area. Default is zero.
- DEFAS=VAL

Sets the default value for MOS source diffusion area. Default is zero.
- DEFL=VAL

Sets the default value for MOS channel length. Default is \(100 \mu \mathrm{~m}\).
- DEFW=VAL

Sets the default value for MOS channel width. Default is \(100 \mu \mathrm{~m}\).
- DEFNRD=VAL

Sets the default value of MOS parameter nRD. Default is zero.
- DEFNRS=VAL

Sets the default value of MOS parameter nRs. Default is zero.
- DEFPD=VAL

Sets the default value for MOS drain perimeter. Default is zero.
- DEFPS=VAL

Sets the default value for MOS source perimeter. Default is zero.
- ELDOMOS

Sets option acm together with the items listed below:
- sets the default value of \(\boldsymbol{T N O M}=25\) instead of the normal 27
- if \(\boldsymbol{L D}\) is not specified, \(L D=0.75 \cdot X J\)
- \(I d s=I d s+g m i n \cdot V d s\)
- for \(\boldsymbol{R L E V}=5\) : (if \(\boldsymbol{d e f n r d} \& \boldsymbol{d e f n r s}\) not defined)
sets the default value of \(N R D=0\)
sets the default value of \(N R S=0\)
- if (accusim2), sets a lower limit for Isat which is \(1 \times 10^{-18}\) for BSIM2 and \(1 \times 10^{-15}\) for any other model
- calls the impact ionization model if !accusim2 \& !BSIM2
- required for the usage of LEVEL 17 (SPICE-A LEVEL 8)
- allows the separate use of both COX and TOX at the same time for Levels \(1,2 \& 3\)
- for Level 2:
uses \(\operatorname{CAPLEV}=4\) for the calculation of the intrinsic charges \& capacitances
- for Levels 1, 2, 3, 16 \& 17:

Leff \(=L d r w a n \cdot L M L T+X L-2(L D+D E L)\)
Weff \(=\) Wdrwan \(\cdot W M L T+X W-2 W D\)
- for Levels \(1,2,3,16 \& 17\) :
uses SPICE-A mobility temperature equations
uses SPICE-A surface potential (Phi) temperature equations according to TLEVC uses SPICE-A VBI \(\cdot V T O\) temperature equations according to TLEV
- for the AMS model Level 15:
uses another capacitance model rather than SPICE 2G6 if \(\boldsymbol{C A P O P}=0\)
- switches automatically:

Level1 \(\Rightarrow\) Level 11
Level2 \(\Rightarrow\) Level 12
Level3 \(\Rightarrow\) Level 13
- if !BSIM2 \& !MOSP9: adds 2WD to Weff used for the calculation of the overlap capacitance to cancel the effect of the already subtracted \(2 W D\).

\section*{- FNLEV}

Selects between the two flicker noise models of the BSIM3v3 model with nотмоD=1\&4.
- GMIN=VAL

Sets the conductance value that is placed in parallel with all PN junctions and drain and source nodes of MOSFET models. It enhances the convergence properties that are degraded by having too low a value of OFF conductance for PN junctions and MOSFET devices. Large values of GMIN may cause unreasonable circuit response. Default is \(1.0 \times 10^{-12}\).
- GMIN_BJT_SPICE

A defect was fixed in the BJT level 1 and 5 models for the Gmin handling. This defect caused unrealistic high leakage current values. This defect was also found in the original Spice code. The fix affects the backward compatibility of results in some test cases. Use option GMIN_BJT_SPICE to reproduce results for backward compatibility.
- GMINDC=VAL

Similar to option GMIN, however the value specified via GMINDC is used for DC analysis only. Defaults to GMIN.
- GRAMP=VAL

Ramps the conductance value that is placed in parallel with all PN junctions of all devices, and all drain and source nodes of MOSFET models, from GMIN \(\times 10^{\text {GRAMP }}\) down to GMIN.

This helps DC convergence in some circuits. This option may also be used in conjunction with the .RAMP command. Default value is 0 . See ".RAMP" on page 852 .
- GENK [=VAL]

Forces Eldo to generate 2nd order mutual inductors. It is activated if val is any value greater than zero or if no value is stated. If option Compat is set it is automatically activated and can be deactivated using GENK=0. Used together with the kLIM option.
- HIER_SCALE=0|1
"S" parameter subcircuit scaling. Forces Eldo to overwrite the global SCALE by the parameter " S " specified in an X instance call. By default, option SCALE is global and applies to all instances. For example:
```

.option SCALE=1u HIER_SCALE=1
.subckt foo d g
m1 d g 0 0 n w=100 l=50
.ends
.subckt foos d g
m1 d g 0 0 n w=10 l=5
.ends
x1 1 2 foo
x2 1 2 foos s=10u

```

The width, w, of X1.M1 will be computed as \(100 \times\) SCALE \(=100 \mathrm{u}\). The width, w, of X2.M1 will be computed as \(10 \times \mathrm{X} 2 \times \mathrm{s}=10 \times 10 \mathrm{u}=100 \mathrm{u}\).
- IBIS_SEARCH_PATH="FILEPATH"

Specifies the path to the directory to search for IBIS files.
- KLIM=VAL

Used together with the GENK option to force Eldo to generate 2nd order mutual inductors. Default is 0.02 .
In the case of the following example:
K1 L1 L2 val1
K2 L1 L3 val2
by specifying the Genk option, a new mutual K3 between L2 and L3 will be generated, if there is no such mutual already present in the netlist. The value of the new mutual created would be vall×val2, and the mutual coefficient is only created if vall \(X_{v a l 2}\) is higher than the value of кцim. However, the new mutual k 3 will not be generated if:
- GENK is equal to zero,
- the mutual coefficient is lower than the value of KıIm, or
- a mutual is already present in the netlist.

A list of the mutuals, which are automatically created, is dumped in the ASCII output file.
- MAXADS \(=\mathrm{VAL}\)

Sets the maximum value for the MOS source diffusion area or drain diffusion area. No default is specified.
- MAXL=VAL

Sets the maximum value for the MOS channel length. No default is specified.
- MAXPDS=VAL

Sets the maximum value for the MOS source diffusion perimeter or drain diffusion perimeter. No default is specified.
- MAXW=VAL

Sets the maximum value for the MOS channel width. No default is specified.
- MINADS = VAL

Sets the minimum value for the MOS source diffusion area or drain diffusion area. No default is specified.
- MINL=VAL

Sets the minimum value for the MOS channel length. No default is specified.
- MINPDS=VAL

Sets the minimum value for the MOS source diffusion perimeter or drain diffusion perimeter. No default is specified.
- MINW=VAL

Sets the minimum value for the MOS channel width. No default is specified.
- MINRACC=VAL

If the resistor value is below minRAcc, Eldo will not create access resistor of devices MOS, BJT, Diode or JFET. Default is undefined, that is, access resistors are always created.
- MINRESISTANCE=VAL

Using this option is equivalent to using the options RMMINRVAL and MINRVAL. Resistors with a value less than the specified VAL will be removed before partitioning occurs and a zero voltage source will be inserted between the two pins, and then one of the pins removed. The resistor cannot be reactivated when this option is used. Resistors that are connected to a pin which appears in a . subckт line, will not be removed.
To allow a resistor to override this option use the KEEPRMIN parameter, see "KEEPRMIN" on page 125. For resistors connected directly to a voltage source, see option

\section*{RAILRESISTANCE.}
- MINRVAI \(=\) VAL

Removes resistors with absolute values below val. It emulates a zero voltage source between the two pins of the resistor. By default, minRval is not specified. This means that no action will be taken regarding resistor devices.

To allow a resistor to override this option use the KEEPRMIn parameter, see "KEEPRMIN" on page 125 .

\section*{Note}

The connection is not allowed in a case where suppression of the resistor would create a Voltage loop. For the same reason, (that is, prevention of a Voltage loop) resistors connected to Y elements are never removed.
To prevent cases where the resistor value would become larger than minRval in a new simulation, the resistor is reactivated. This could happen in instances where the resistor's value is controlled by a parameter, varying according to a .STEP command for instance.
- mnumer

Applies to MOS devices. Sets the derivative computation method to the finite difference method (DERIV=0). By default, DERIV=1 for analytical derivatives.
- MOD4PINS

Sets the number of pins that must be specified in the MOS instantiation to 4. (The only model that can have more than 4 pins is the BSIMSOI3 model.) Setting this option has the effect that for the following line:
```

M1 D G S B MOD W L AD AS PD PS NRD NRS M=<value>

```

MOD is considered as the model name. Otherwise, Eldo would look for a model named nRS, with M1 assumed to have 12 pins.
- MODMONTE [=0|1]

Compliance with TSMC TMIv2. This option only has an effect on Monte Carlo analysis parameter variations specified via GAUSS/AGAUSS/UNIF/AUNIF. When set to 1, Eldo will extract a new random value for each usage of the parameter. When set to 0 (default), there is only one extraction per X instance.
- MODWL

This option is not required because it is set by default. MOS model versions are selected via . MODEL command w and \(\mathbf{L}\) parameters (binning parameters). Use option nomodwl to switch off the functionality.
For further details please see "Selection of MOSFET Models via W/L Specifications (Binning)" on page 257.

\section*{- MODWLDOT}

This option is used for binned models. By default, the extension of a binned model is either: <root>.<extension> or <root>_<extension>
This can be confusing when <root> also contains the character "_". Specify option моDwLDOт to only allow "." as the separator. When set, the character "_" can be used in the <root>. This option is automatically activated with the -compat flag. See also "Selection of MOSFET Models via W/L Specifications (Binning)" on page 257.
- NGATEDEF [=node_name ]

Specifies NMOS floating gates to be connected to the specified node name. Default is node 0.
- nOACDERFUNC

The option acderfunc is set by default (beginning Eldo v6.8). Specify noacderfunc to disable this for backward compatibility. See also "ACDERFUNC" on page 983. Device objects can be individually set with the Acderfunc local parameter. The specification on the device overrides any global setting by options acderfunc or noacderfunc.
- nOAUTOCTYPE

Disables automatic checking by Eldo of the dependencies of the capacitor value. Without this option, if Eldo finds that the capacitor value does not depend on the bias across the terminal of the capacitor, then Eldo will behave on that device as if CTYPE=1 had been set. With this option set, Eldo will behave as if CTYPE \(=0\) (default) has been set, unless it is otherwise explicitly specified.
- NOCATMX

Disables merging devices in parallel. This option is equivalent to the -nocatmx commandline flag. For further details see "Merging Devices in Parallel" on page 120.
- NOMODWL

By default, MOS model versions are selected via .model command wand larameters (binning parameters). Specify this option to unset this behavior.
For further details see "Selection of MOSFET Models via W/L Specifications (Binning)" on page 257.
- NWRMOS

Forces all access resistors of MOS that are connected to nodes which are to be solved by NEWTON, to be created as objects, that is, as if the access resistors had been explicitly instantiated in the netlist. This is for improved accuracy. Default is nwrmos.
- PGATEDEF[=node_name]

Specifies PMOS floating gates to be connected to the specified node name. Default is node 0 .
- RAILINDUCTANCE=VAL

This option is similar to the RAILRESISTANCE option. Inductors connected directly to a power supply or ground and below the specified value VAL will be replaced by a short circuit. The idea is to remove effects of small inductance added between power supply and the actual circuitry in order to speed up simulation. The inductor cannot be reactivated when this option is used.
- RAILRESISTANCE=VAL

This option is similar to the MINRESISTANCE option. Resistors connected directly to a voltage source and below the specified value VAL will be removed. A zero ohm resistor will
be inserted between the two pins, and then one of the pins removed. The resistor cannot be reactivated when this option is used.
- reduce

This option is set by default. Multiple identical resistors, diodes, BJTs, MOSFETs, and subcircuits that follow each other are reduced into a single instance using the device multiplier м parameter, for example:
```

x1 1 2 FOO A = 1 B = 1
x2 1 2 FOO A = 1 B = 1
x3 1 2 FOO A = 1.0 B = 1

```

Here, X instances x 1 and x 2 will be replaced by:
\(\mathbf{x} 112 \mathrm{FOO} \mathrm{A}=1 \mathrm{~B}=1 \mathbf{M}=2\)
but x 3 will remain as it is because the character string for A does not match.
For more information see "Combining Identical Resistors" on page 126, "Combining Identical Diodes" on page 227, "Combining Identical BJTs" on page 234, "Combining Identical MOSFETs" on page 252, and "Combining Identical Subcircuits" on page 303 respectively.
- RESNW=val

Resistors with values higher than resnw are allowed to be solved by OSR. Default is \(1.0 \mathrm{e} 18 \Omega\) (that is, virtually infinity).
- RMMINRVAL

With this set option minRVAL=val will emulate a . Connect through the 2 pins of the resistor. The advantage of this is that it reduces the number of nodes to be solved, but the disadvantage is that the resistor cannot be reactivated.
To allow a resistor to override this option use the keeprmin parameter. For more information see "KEEPRMIN" on page 125.
- RMOS

When this is set, all MOS access resistors are unconditionally created as objects. Default is normos.

Note
Whenever MOS access resistors are not created as objects, Eldo uses an iterative process to handle their effects. This process is less CPU time consuming than the resolution of the additional nodes which are created to connect the access resistors to the MOS devices.
- RSMALI=VAL

Resistors with a value smaller than val will be set to val. Default is \(1.0 \mathrm{e}^{-6} \Omega\).
- \(\quad \mathbf{R Z}=V A L\)

This will set the global value (VAL) for Rz which will enable Eldo to detect a ' \(Z\) ' state on all A2D nodes when the option ZDETECT is used. A ' \(Z\) ' state is detected when the equivalent impedance of the A2D node exceeds the specified Rz value.
- SCALE=VAL

Multiplier for MOS width, length, perimeter of drain and source. The parameters \(A D\) and as are multiplied by \(x^{2}\). The default value of scale is 1.0.

For more information on these parameters, refer to the Device Models chapter. For more information on scale factors see "Scale Factors" on page 73. The keyword scale can be used in expressions. For more information on such keywords see "Reserved Keywords" on page 72.
scale can also act as a multiplying factor for diodes, according to the value of the scalev parameter of the diode model, see Level 1 Scaling in the Eldo Device Equations Manual.
For .extract function eval (device_name, device_entity) to take into account the option scale multiplier specify option extract_eval_final. See
"EXTRACT_EVAL_FINAL" on page 1000.
- (NO) KWSCALE
sCale can be considered as a keyword by Eldo (kwscale set), or not (nokwscale is set). The default condition is as if option kwscale has been explicitly declared on the netlist, meaning that scale is a keyword. The default value of scale is 1.0 .
When scale is considered as a keyword, scale can appear in expressions, and its value will be that assigned via option SCALE=val.
When scale is not considered as a keyword, scale can also appear in expressions, but its value must be defined via a .PARAM statement, as is the case for any other parameter.
When -compat is set at invocation of the simulator, nokwscale is assumed to be set, and can be switched with option kwscale.
When -compat is not set at invocation of the simulator, kwSCALE is assumed to be set, and can be switched with option nokwscale.
- SCALEBSIM=VAL

Scales all sensitivity parameters of the BSIM1 and BSIM2 MOSFET models. For example, VFB is a basic parameter which is corrected by the length and width sensitivity parameters, lvfb and wVfb. scalebsim will scale these parameters by the factor val. Default value is 1, for example:
\[
v f b=V F B+(L V F B \cdot S C A L E B S I M / L)+(W V F B \cdot S C A L E B S I M / W)
\]
- \(\quad\) SCALM=VAL

Scaling factor for the model parameters LDIF, dl and dw (MOS), Dw and dlr ( RC wire), for example DL is equivalent to the LVAR parameter for the MM9 models (see the "Philips MOS 9 Model (Eldo Level 59 or MOSP9)" on page 283). scalm can be
individually defined for each model card using the model parameter sCALM. This overrides the global sCalm value defined using the .option command.

For more information on these parameters, refer to the Device Models chapter.
- SHRINK_FACTOR=VAL

Specifies a value to multiply the scale value by to obtain the effective scale value. In case of multiple definitions, the effective scale value is the product of the last specified sCALE value and the last specified Shrink_factor value. Shrink_factor defaults to 1.0 .
- SOIBACK=<grounded_voltage_source>

This option applies to the SOI model only (BSIMSOI3 model). Instances of such models can accept 4 or 5 pins in the netlist. When the soiback option is specified and the MOS device is defined as a 4 pin device, then the 4th pin is the internal body of the device. This option defines a voltage source allowing Eldo to translate a 4-pin SOI instance into a 5-pin SOI instance. The backgate will be inserted and connected automatically to the voltage source defined by the soiback option.
- SPMODLEV

Beginning Eldo v6.5 the SP model was enhanced with analytical derivatives. Analytical derivatives replace the numerical derivatives and improves the speed of the model. By default Eldo uses the new implementation. To select the old model implementation, set the Eldo option SPMOdLev for backward compatibility.
- TMAX \({ }^{\text {TMIN }}=\) VAL

Some models contain self-heating effects, such as VBIC or Hicum models. For such models, when self-heating is active, the temperature of the device becomes an unknown to the system. In order to prevent possible overflow in model evaluation, device temperature is limited by Eldo, and by default cannot exceed 1000 K , or go below 0 K . These values can be overwritten using options \(\operatorname{TMIN=VAL}\) or TMAX=VAL.
- USEDEFAP

If the model parameter ACM is set to 2 or 3, then AD, AS, PD and PS, when unspecified in the instance command, are computed from \(\mathbf{w}\), \(\mathbf{L}\) and hDIF, regardless of what values are given to defad, defas, defrd and defps. If you wish to use defad, defas, defpd and defrs, option usedefap has to be set.
- WARNING_DEVPARAM

Forces Eldo to print a warning instead of an error when an unknown parameter is specified on a device instance. For example:
```

ERROR 254: OBJECT "M1": Unknown parameter MULUO

```
will be replaced by:
Warning 209: OBJECT "M1": Parameter ignored MULU0
- WARNMAXV=VAL

Returns a warning if a Voltage on a node is higher than VAL. This applies to DC analysis only.
- wL

Reverses the order of MOS length and width specification.
- ymfact

Allows the use of the device multiplier \(m\) in \(Y\) instantiations. This must be specified at the beginning of the netlist.
- zdetect

When this option is set, it will enable Eldo to detect ' \(Z\) ' states on A2D nodes where an \(R z\) value has been specified either in the .A2D/.model card or with the option RZ=VAL. A ' \(Z\) ' state is detected when the equivalent impedance of the A2D node exceeds the specified \(\mathbf{R z}\) value command.

\section*{Reduction Options}

Refer to the chapter "Eldo Reduction" on page 1085.
- REDUCE_KEEP_OUTPUTS=YES \(\mid\) NO

See "Reduction Options" on page 1097.
- REDUCE_KEEP_NODE=node_name

See "Reduction Options" on page 1097.
- REDUCE_KEEP_INST=instance_name

See "Reduction Options" on page 1097.
- REDUCE_MAX_CAP=value

See "Reduction Options" on page 1097.
- REDUCE_MAX_IND=value

See "Reduction Options" on page 1097.
- REDUCE_MAX_RES=value

See "Reduction Options" on page 1097.
Note
For backward compatibility, the old (pre-2009.1 release) "RC_REDUCE_*" options are still accepted for reduction. A warning message is displayed to inform you that this syntax is deprecated, suggesting to use . Reduce commands instead for greater efficiency. If both syntax is found in a netlist then the newer . Reduce syntax takes precedence.

\section*{Noise Analysis Options}
- FLICKER_NOISE=VAL

Used in Noise Analysis as a frequency dependent noise model selector. Default value is zero. Values \(0,1,2,3\) are used. Same functionality as using the flklev model parameter.
- thermal_noise=Val

Used in Noise Analysis as a temperature dependent noise model selector. Five values are used: \(0,1,2,3,4\). Same functionality as using the thmiev model parameter.

See the appropriate sections in the Device Models chapter for details of the device noise models used for each case for the above two noise analysis options.
- IKF2

Specifies that the onoise value returned is in \(V^{2} / \mathrm{Hz}\), instead of \(V / \sqrt{\mathrm{Hz}}\).
- JTHNOISE=VAL

Selects the equations for thermal noise in JFETs. The equations are as follows:
```

JTHNOISE=0

```

Default equation is used: \(i d=\frac{8 k T}{3} \cdot g m\)

JTHNOISE=1
If vds \(>\) vdsat \(\operatorname{Sid}=\frac{8 k T}{3} \cdot g m\)
Else Sid \(=4 k T \cdot(g m+g d s)\)
JTHNOISE=2
Sid \(=\frac{8 k T}{3} \cdot(g m+g d s) \cdot\left(\frac{3}{2}-\frac{V d s e f f}{(2 \cdot V D S A T)}\right)\)
where \(V d s e f f=\min (V d s, V D S A T)\)
- nonoise

By default, it is assumed that all devices contribute to the total output noise, unless this option is specified. Setting nonoise assumes all devices to be noiseless.
- NOISE_SGNCONV

Allows the user to change the sign convention used for the computation of the noise parameters ворт and Phi_OPt.

\section*{Simulation Display Control Options}
- ACSIMPROG

This option displays in the terminal window the simulation progress (percentage) during an AC analysis. This can be useful to monitor long simulations.
- DCSIMPROG

This option displays in the terminal window the simulation progress (percentage) during a DC analysis. This can be useful to monitor long simulations.
- ENGNOT

Prints numerical values in engineering notation, with scaling factors (for example \(\mathrm{U}, \mathrm{MEG}\) ). Applies only to data generated by the .OP command, to data corresponding to DC values, or to data corresponding to .PRINT statements, and .EXTRACT or .mEAS values. This is similar to option INGOLD, whichever is specified last takes precedence.
- INGOLD=VAL

Controls the printing of double precision numbers in engineering or exponential format. VAL can be 0,1 or 2 . This is similar to option ENGNOT, whichever is specified last takes precedence.

INGOLD=0
Use engineering format: exponents are given from a single character with the same convention as that for the input file. However, the 1.0 e 6 is expressed as X rather than as MEG.

INGOLD=1
Fixed and exponential. Numbers between 0.1 and 999 are written without exponential format. Other numbers use the exponential SPICE 2G6 format.

INGOLD=2
Exponential SPICE 2G6 format. This is the default.
- LOCAL_NOWARN [ [=]msgid]

Suppress warning messages in a local context only. Similar in functionality to option NOWARN (globally suppress warning messages). By default, all warnings are displayed by Eldo. If specified in a file included with . Lib or . INClude, then only the display of warnings issued in this file and its descendants will be suppressed. As a consequence specifying LOCAL_WARN in the top netlist is equivalent to option NOWARN.
Specifying Local_nowarn with the message ID value means only warning msgid will not be printed by Eldo.
- MAXTOTWARN[=VAL]

By default, all warnings are displayed by Eldo. This option limits the total number of warning messages displayed; only val number of warnings will be displayed. Default is 0 , meaning this is disabled.
- MAXWARN=VAL | MAXWARNmsgid=VAL

By default, all warnings are displayed by Eldo. This option limits the number of warning messages displayed for each warning number. For example, MAXWARN=2 specifies that a maximum of two messages will be displayed for each intended warning.
Specifying the message ID, msgid, is similar to above but only the maximum number of messages for warning msgid is explicitly specified, and therefore has precedence over the MAXWARN value. For example: maxwarn \(125=2\) specifies that no more than two messages of warning number 125 will be displayed.
- MSGBIAS [=VAL]

Usually there will only be three messages mentioning that PMOS are connected to 0 . Use the msGbias option without specifying a value if you want all such messages, or specify a limit with VAL.
- MSGNODE=VAL

Limits the number of node connection faults reported. Eldo reports four types of node connection faults as follows:
```

Warning 107: node "xxx": Less than two connections.
Warning 108: node "xxx": This node is a floating gate.
Warning 113: node "xxx": Not connected to any element.
This node is removed from the netlist.
Warning 252: OBJECT "xxx": Self-connected object not created.

```

If MSGNODE=0 then all connection fault warnings are displayed. By default, MSGNODE is set to 3, which means Eldo displays each type of connection fault for the first three nodes on which the fault is detected. If the number of nodes at which a fault is detected exceeds the number specified by this option, then the following warning message is issued:
```

Warning 29: Set .option MSGNODE=0 to receive all such warnings.

```
- NOWARN[ [=]msgid]

By default, all warnings are displayed by Eldo. Specify nowarn without any value to suppress the display of all warnings. This option must be placed at the top of the design, just after the title line, otherwise the warnings will continue to be displayed.
Specifying nowarn with the message ID value means only warning msgid will not be printed by Eldo. Similarly, this option must be placed at the top of the design, just after the title line.
- NUMDGT=INTEGER_VAL

Specifies the number of significant digits printed for numerical values written to the ASCII output file. Controls the print accuracy; the simulation accuracy is not affected. Applies only to data generated by the .or command, to data corresponding to DC values, or to data corresponding to .PRINT/.PRINTFILE statements, and .EXTRACT or .MEAS values. Default is 5 digits.
- PRINTLG=VAL

This option is used for printout purposes only: if number of items which appear in a .PRINT card exceeds printlg, values are printed out in different tables. This is to prevent lines being too long in the ASCII output file, making reading of the file uncomfortable for the user. Default is 8 .
- VERBOSE

This option forces Eldo to display more detailed reporting with some information messages in the standard output terminal. Eldo will print hints about syntax which is valid but ignored if the appropriate analysis is not found in the netlist. For example:
```

Warning 10001: No optimization command has been found in the netlist.
As a consequence:
1) .option OPSELDO_NETLIST is ignored
2) .PARAMOPT are interpreted like .PARAM using the initial value,
or ignored if no initial value has been specified.
3) GOAL=MINIMIZE is ignored on measurement FOO
4) GOAL is ignored on measurement FOO2
5) UBOUND is ignored on measurement FOO3
6) GOAL=MAXIMIZE is ignored on measurement FOO4
Warning 10002: COMMAND .MC has not been found in the netlist.
As a consequence:
1) .option DISPLAY_CARLO is ignored

```
- WARN[ [=]msgid]

Specify to cancel any NOWARN/LOCAL_NOWARN option specifications as soon as they are encountered. If a message ID, msgid, is specified then only warning msgid is enabled.

\section*{- wBULK}

Eldo would print out a warning about positive bias on NMOS bulk (or negative bias on PMOS bulk) only once, unless wbulk is set. When set, all warnings will be printed out.

\section*{Simulation Output Control Options}
- acout=VAL

This option controls how expressions \(V X(a, b)\) and \(I X(a, b)\) are computed in AC analysis: x in this case stands for \(\mathrm{DB}, \mathrm{m}, \mathbf{P}\) or GD . Only two values are allowed, 0 or 1 . In -compat mode, ACout defaults to 1 , else it defaults to 0 .

0
\(\mathbf{v X}(\mathrm{a}, \mathrm{b})\) or \(\mathrm{IX}(\mathrm{a}, \mathrm{b})\) are computed from the complex value \(\mathbf{v}(\mathrm{a})-\mathbf{v}(\mathrm{b})\) or from i(a)-i(b).

1
\(\mathbf{v x}(\mathrm{a}, \mathrm{b})\) or \(\mathrm{IX}(\mathrm{a}, \mathrm{b})\) are computed from the complex value \(\mathbf{v X}(\mathrm{a}, 0)-\mathbf{v X}(\mathrm{b}, 0)\) or from \(\operatorname{IX}(a, 0)-I X(b, 0)\).
- ALTER_NOMINAL_TEXT

This option allows to attach a label to the nominal run. For .ALTER, the label follows the command, for example: .alter <label>. This text is printed in the aex file or attached to the JWDB waveforms.
- ALTER_SUFFIX

Change the naming convention for swept waves used in .ALTER statements to be switched between: \(x x x\) and \(x x x \_\)alter: \(X X\).
- ASCII

Forces Eldo to store the results including the printing of the output curves in the ASCII output .chi file. The default behavior is not to store the results in the ASCII output file (that is, NOASCII is the default). This option is equivalent to the -ascii command-line flag of Eldo. The size of this file can increase significantly for large simulations when these results are printed inside it. Affects .PLOT and .PRINT commands.
- ASCIIPLot

Forces Eldo to plot the waves in the ASCII .chi output file. By default, wave information is only written to the binary output . \(w d b\) file, with print tables in the .chi file.
- BLK_SIZE=VAL

Sets the total size of the buffer when using the 4.7 cou file format. With this cou file format, data is buffered. The format is k values for X -axis, followed by k values for wave 1 , then k values for wave 2 and so on. The value of ' \(k\) ' (that is, the size of the buffer) is computed by Eldo according to the number of waves. Specified in Octets. Default is 1 e 6 (that is, 1 Meg ).
- captab

Prints out in the ASCIII .chi output file the capacitance values which are placed in the AC matrix. The term Cij corresponds to the derivative of the charge on node ' i ' with respect to the voltage on node ' j '. CAPTAB must be used in conjunction with a .AC, . OP or .TRAN command. Information will not be output when there is only a .DC command. The output in the ASCII file has the following format:
```

Node <i>
<j1> C = <val1>
<j2> C = <val2>
CFIX = <valfix> CVAR = <valvar> CTOT = <valtot>

```
where:
vall is the derivative of the charge on node ' i ' with respect to the voltage on node ' j 1 ', and so on.
valfix is the total capacitance connected to node ' i ' which is not dependent on other node voltages.
valvar is the total capacitance connected to node ' i ' which is dependent on other node voltages.
valtot is the sum of valfix and valvar.
- COLLAPSE_DSPF_OUTPUT [ = @ \| \# ]

When set, Eldo will regroup currents (I, Ix, Isub) and noise outputs according to the device or subckt instance specified in arguments. By default the DSPF character is set to @. (Character \# can also be specified with this option.) For example, the equivalence for currents can be expressed with the SIGMA() operator:
```

Ix(X1.1) is equivalent to SIGMA(Ix(X1.1), Ix(X1@*.1))
I(R1) is equivalent to SIGMA(I(R1), I(R1@*))

```

Whereas noise outputs are SQRT (sum (NOISE(...) ^2)):
NOISE(X1) is equivalent to:
SQRT (NOISE(X1)^2 + NOISE(X1@2)^2 + ... NOISE(X1@n)^2)
Limitation: the printing of noise in the .chi file will still report the parasitic devices.
- CONTINUOUS_FFT

Specifies the waveform viewer to represent the FFT wave in continuous mode instead of the default spectral representation. This modifies the .swd file only; FFT waveforms are still saved in the.\(w d b\) file as spectral. Can alternatively be specified with the (continuous) keyword on the .рLот command.
- DEFRMSNTR

When a .noisetran simulation is requested, transient analysis extracts by default return only nominal values, see ".NOISETRAN" on page 747. For backward compatibility (prev2008.2), specify this option for Eldo to return both RMS and nominal values. In such a case, .EXTRACT TRAN extracts (or extracts without any analysis type) will return both RMS and nominal values: RMS values computed by .nOISETRAN, nominal values from the nominal transient analysis. This only has an effect for .nOISETRAN simulation with multiple run MRUN specified.
- DISPLAY_CARLO

Display all the updated values for all the Monte Carlo and Worst Case runs.
- DUMP_EXTRACT=0|1

Save single datapoint extract results (for example, scalars) in the . \(w d b\) file, so that they can be compared between . \(w d b\) files.

0
Default. Do not save single datapoint extract results in the.\(w d b\) file.
1
Save single datapoint extract results in the.\(w d b\) file.

\section*{- DUMP_MCINFO}

Write a summary of the .EXTRACT distributions during Monte Carlo analysis to the .aex file and the file declared by the .extract parameter file=fname, if they are specified. The information is also written to the .chi file.
- EMPTY_MCHISTO

Forces Eldo to create single point histograms for .Extract commands which show no variations during a Monte Carlo analysis. By default no histogram is generated for such extracts. This option is similar in functionality to the histo_zero option.
- extcgs

The default unit for .EXTRACT current values (I(object_name)) is Amperes (since Eldo v6.5_2). Set this option to specify mA as the default unit for backward compatibility.
- extfile

Enables the generation of a .ext or .ext. \(w d b\) file depending on the output format.cou or . \(w d b\). Extraction results are by default saved inside the EXT folder in the main . \(w d b\) file. By default, the extraction results file (.ext or .ext.wdb) is not automatically created.
- EXtMKSA

When set, the . еxtract values which are relevant to the transient-extract language are expressed in \(m k s A\) (meter-kilogram-second-Ampere) units instead of \(c g s\) (centimeter-gramsecond) units, that is, if extmises is set, a result such as:
```

TPDUU(V(1),V(1),VTH=0.5) = 1.0001E+06 nS

```
would be returned as:
```

TPDUU(V(1),V(1),VTH=0.5) = 1.0001E-03

```
- EXTMOD_GENWAVE

If this option is set, the extract-mode will use the run parameters from the input database to regenerate a.\(w d b\) file containing EXT folders only.
- EXTRACT_EVAL_FINAL

When specified, . EXTRACT function EVAL(device_name, device_entity) will take into account the scale factor, option sCALe, if specified. The value returned will be the value computed by the Eldo parser, multiplied by the scale factor. When this option is not specified, the value returned by .EXTRACT function EVAL (device_name, device_entity) is the value computed by the Eldo parser, before any scale factor effect is applied. For example:
```

.param p1 = 1u
.param p2 = p1*2
M1 ... w = p2
.option scale = 3
.extract eval(m1,w)

```

By default, Eldo will return an extracted value \(2 u\), that is, the value of p 2 . If option extract_eval_final is set, Eldo will return an extracted value of 6 u , that is, the value of p2 multiplied by scale.

\section*{- EXTRACT_VECT_AXIS=INDEX|XAXIS}

Controls the type of x-axis used for vector .ехтRACT waveforms in the .wdb output file. It applies only to "Transient Extraction Language Functions" on page 645 (those extracted at run-time) used in conjunction with the vect keyword. The default value is index, extract vectors are plotted versus an increasing abstract index. When set to xaxis, extract vectors are plotted using the same x -axis as normal waveforms, and values are saved at the time they have been measured. For example:
```

.option EXTRACT_VECT_AXIS=XAXIS
v1 1 0 sin(0 1 1meg)
r1 1 0 1
.tran 1n 5u
.extract tran vect trise(v(1),vl=0.2,vh=0.8)
.end

```
- histlim

In case History has to be saved on FAS, histlim would save data only if there is a significant change (based on reltol) between the last saved value and the current value. This is in order to conserve memory when running very long transient simulations.
- hISTO_ZERO

Forces Eldo to create a histogram of .EXTRACT commands even if the range of variation is 0 . By default, when the range is 0 (when the . extract/.meas is not affected by Monte Carlo changes), no histogram is generated. This option is similar in functionality to the EMPTY_MCHISTO option.
- INPUT

Forces a list of the user-specified inputs present in the netlist to be written to the binary output file (.wdb) for checking purposes.
- INFOMC=filename

Forces Eldo to dump the information in the specified filename instead of in the .chi file. This function emulates option DISPLAY_CARLO.
- JWDB_ACTRAN_USE_TIME

Instructs Eldo to use the time value, instead of an absolute counter, to name the AC or NOISE folders which are created in the.\(w d b\) file during transient analysis. By default, they are named AC_1, AC_2, and so on. If this option is set, they will be named AC_20.000N, AC_50.000N, and so on.
- JWDB_EVENT

Specifies the time interval in seconds for updating marching waveforms displayed in the EZwave viewer. Default value is 10 s .
- JWDB_EXTENSIONS \(=0 \mid 1\)

When set to 1 , enables modifications in the way results are stored inside.\(w d b\) files. The compound waveform is not created when . MC irun \(=\mathrm{x}\) is used (since this is a single simulation). Default is 0 .
- JWDB_PERCENT

Specifies the simulation percentage interval for updating marching waveforms displayed in the EZwave viewer. Default value is \(5 \%\).
- KEEP_DSPF_NODE

This option forces Eldo to keep the original .PLOT/.PROBE command if a node coming from the DSPF has the same name. It is not set by default because this node may be completely different than the original one. When a node is replaced by a parasitic net using a DSPF file, this node can be renamed or even removed from the design. This is why .PLOT/.PROBE commands referencing a node modified by a DSPF file generate a compound waveform regrouping the parasitic nodes.
- KEEP_HMPFILE

Generates the .hmp output file for transient noise analysis results, see ".NOISETRAN" on page 747. The .hmp file, of COU format (a legacy format), contains results for each NOISE analysis. By default, it is not generated. If the nonom parameter is specified, then this option is always ignored and the . hmp file is not generated, This is because only one run, the noisy run, is performed. This is written directly to the regular .wdb file, without the need for an extra .hmp file, which is only used to compute RMS values when the simulation is complete.
- LCAPOP

Synonymous with the сартав option. Prints out in the ASCII .chi output file the capacitance values which are placed in the AC matrix. The term Cij corresponds to the derivative of the charge on node ' i ' with respect to the voltage on node ' j '. LCAPOP must be used in conjunction with a .AC, .OP or .TRAN command. Information will not be output when there is only a .DC command. The output in the ASCII file has the following format:
```

Node <i>
<j1> C = <val1>
<j2> C = <val2>
CFIX = <valfix> CVAR = <valvar> CTOT = <valtot>

```
where:
vall is the derivative of the charge on node ' i ' with respect to the voltage on node ' j 1 ', and so on.
valfix is the total capacitance connected to node ' \(i\) ' which is not dependent on other node voltages.
valvar is the total capacitance connected to node ' i ' which is dependent on other node voltages.
valtot is the sum of valfix and valvar.
- LIMPROBE=VAL

Sets the maximum number of nodes that may be monitored via the . Probe command. Default value is 10,000 .

\section*{- LIST}

Causes a listing of the elements contained in a circuit netlist, together with the names of their pins, to be printed to the ASCII output (.chi) file. Grounded capacitors are not considered as elements.
- MAX_CHECKBUS=ALL|val

This option allows the user to control the number of checkbus errors printed to the .chi file. Default value is 20 . Specifying 0 means no errors are printed. ALL specifies all errors are printed (this can also be set by specifying -1). Also if the .checkbus command has specified the Lock parameter then all check points are printed whether they have passed or failed.
- MAX_DSPF_PLOT=VAL

Sets the maximum number of DSPF interface nodes plotted. Default value is 100 . This can be useful when a plot (or probe) in DC or TRAN is asked on a node which has been replaced by a DSPF parasitics network (.DSPF_INCLUDE command), then the plot of this node will be replaced by a plot of all the DSPF network interface nodes. Inside EZwave, the generated plots will be grouped inside an analog bus.
- MC_NOMINAL_OP

Forces operating point (OP) results to be saved for the nominal Monte Carlo run. By default, .mC used without the all keyword disables option probeop, option probeop2, and PSF OP information.
- MEASFILE

Enables the generation of a .meas or .meas.wdb file depending on the output format .cou or . \(w d b\). Measurement results are by default saved inside the EXT folder in the main . \(w d b\) file. By default, the measurement results file (.meas or .meas.wdb) is not automatically created.
- NEWACCT

Specifies that simulation display statistics are displayed in a better format. By default, this option is disabled. When this option is made active, the subsequent output will be generated with one item and one number allowed per line. This simplifies the writing of postprocessors. Example:
```

Number of Input signals 3
Number of resistors 0
Number of floating capacitors 0
Number of inductors 0
Number of voltage sources 3
Number of current sources 0
Number of dependent sources 0
Number of diodes 0
Number of BJT 0
Number of JFET 0
Number of MOS 19
Number of SWITCHES 0
Number of Transmission lines 0
Total number of elements 22
Number of equations 13

```
```

Number of non-zero terms 73
Percent Zeros 5.680e+01
Number Newton iterations 178
Average number Newton iterations 2.000e+00
Number of accepted time steps 57
Number of rejected time steps 4
due to LTE 4
due to newton to Newton 0
Evaluation of active devices 11864

```
- NOASCII

Eldo sets this option by default. It forces Eldo to suppress the printing of the output waveforms in the ASCII output .chi file. The output file is still created, but the size is significantly reduced for large simulations when these results are not printed inside it. This option is equivalent to the -noascii command-line flag of Eldo. Affects . PLOT and .PRINT commands. Specify the ASCII option to force Eldo to store the results including the printing of the output curves in the ASCII output .chi file.
- NOASCIIPLOT

This option forces Eldo to suppress the printing of the plots in the ASCII .chi output file. Information is written only in the binary output . \(w d b\) file.
- NOBOUND_PHASE

Option to avoid the fold-down for the phase. When this option is set, the phase is not displayed in modulo 360 degrees. This option only applies to outputs of type XP() (for example vp()\(, \mathrm{ip}()\) or wp()\()\). It does not apply to outputs of another type, or to the internal representation of waveforms of type phase. Therefore, to avoid fold-down of phase for a computed waveform, it should be written in the form:
```

.plot ac wp(computed_waveform)

```
- NODCINFOTAB

Disables the printout of the DC node information in the ASCII output file. This can be useful to save disk space if the circuit is very large and the DC solution is not of interest.
- node

Causes printing of a node table to the \(\log\) (.chi) file. It contains a list of all elements in a circuit netlist, together with the total grounded capacitance value for each node.
- NODEFRMSNTR

When a .noisetran simulation is requested, transient analysis extracts by default return only nominal values, RMS values are not returned. Transient noise analysis sets this option by default, see ".NOISETRAN" on page 747. Specify option noderrmsntr if only nominal values should be dumped. Use the analysis type NTR on the .EXTRACT command to select computation based on RMS.
- NOEXTRACTCOMPLEX

The . Еетract command by default provides complex results information instead of only real values with the yval function. This can be disabled by setting this option. Complex
results information is used by default instead of real values with the .EXTRACT yval function. For example, .extract ac label=EX1 yval (v(out), 10k) would deliver the result:
```

* EX1 = 10.011 , -1.8

```

The general form is: real_part, imaginary_part.
- nOMOD

Suppresses the print-out of the model parameters to the ASCII output (.chi) file.
- NOOP

Suppresses the printing of operating point (OP) table information in the ASCII output (.chi) file when a . AC analysis is specified.
- nopage

This is synonymous to the option LIST.
- NOSIZECHK

Eldo checks the size of the .chi file, and does not write to it if its size exceeds the total disk space available (Unix Only). The nosizechk option disables this check.
- nosmkмcwc

SOA are computed and dumped for all runs triggered by .mC and .wCASE commands (by default beginning Eldo v6.8). This enables the user to see if SOA are violated or not during MC or WCASE runs. Specify this option to disable this, in which case information will be dumped only for the nominal run.
- notrc

Suppresses the rewriting of the circuit description file in the ASCII output (.chi) file. Only the lines following its declaration in the netlist are suppressed. See also ".NOTRC" on page 752 to fully suppress the description from being rewritten.
- notrclitb

This option removes the printout of .model and . Subckt included from library files via . Lib or .addlib commands.

\section*{- NOWAVECOMPLEX}

Disables the generation of complex waves. By default, complex waveform information is only written to the saved windows file (.swd) with JWDB format output. This option forces Eldo to write complex waveform information to the waveform database (. \(w d b\) ) as well as the saved windows file. This can be used to restore the functionality of Eldo versions prior to v6.3_2. This can also be specified using the -jwdb_nocomplex flag when invoking Eldo.
- noxtabnoise

X instances that do not contain any other X instances are considered as Eldo primitives, and are taken into account in the noise table that is displayed in the ASCII output files. This is
particularly useful in the case of designs where devices are modeled by subcircuit rather than by Eldo primitive. Such X instances will then appear in the ASCII table as if Eldo primitives had been used. This can be disabled with the noxtabnoise option.
- OPALLDC

Creates an "OPERATING POINT INFORMATION" section in the .chi file for each point of a DCSWEEP analysis. The total power dissipation is also reported in the standard output for each point. It does not affect other output files.

The presence of a .op command is not necessary to enable the printing in the .chi file when option opalldc is set.
- OPTYP=VAL

Used to change the way Operating Point information related to MOSFETs is displayed in the ASCII output file. Default: optyp=1. See ".OP" on page 755.
- OUT_RESOL=VAL

Save data in binary waveform output file only if the time increment in the output file is at least the value of out_resol.
- OUT_SMP=VAL

This can be used as an alternative to the freqsmp/timesmp with out_step options. With out_SMP Eldo expects a frequency value to be specified whereas a time interval is expected with out_Step.
- out_Step

Used in conjunction with option \(\operatorname{Freg}\) gsmp=val. Forces Eldo to save into the binary waveform output file only the timesteps in \(1 / \mathrm{val}\) intervals as defined by freqSmp. All intermediate timesteps, although calculated, will not be saved. The results in this output file (using . OPTION FREQSMP=val OUt_STEP in the netlist) are close to those using option FREQSMP=val in the netlist, but not to the output file without option Freqsmp in the netlist.
It is possible to assign expression parameters to out_ster. For example:
```

.PARAM p1 = 1k
.OPTION OUT_STEP = p1

```

\section*{- PARAMETRIC_ACTRAN}

Modifies the way Eldo treats AC or NOISE extracts which are performed during transient (AC + TRAN + OP time). By default Eldo generates a new extract for each time value. When this option is set, Eldo will not generate new extracts but will consider the extract has a parametric waveform with time for sweeping variable.
- \(\boldsymbol{P O S T}[=1 \mid 2]\)

Specifying this option without any value is equivalent to .PROBE \(\mathbf{v}\), but in addition, current values of grounded voltage sources are also displayed.
When \(\operatorname{pOSt}=1\), additional results files are generated as binary files.
When \(\operatorname{POST}=2\), additional results files are generated as ASCII files.

\section*{- POST_DOUBLE}

Save values in output files using double precision. By default output files generated by option \(\operatorname{POST}=1 \mid 2\) are saved using simple precision variables (float). This can lead to accuracy problems in certain cases.
- PRINT_ACOP=0|NO|1|YES

This option will limit the amount of operating point information produced in the output file, when a .AC analysis is specified.
- PRINTfile_Step=VAL

Defines a default global value for all .PRINTFILE commands that do not have a specific STEP value.
- PRINTFILE_FREQ_STEP=VAL

Defines a default global value for all time-based .PRINTFILE commands that do not have a specific STEP value.
- PRINTFILE_TIME_STEP=VAL

Defines a default global value for all frequency-based .PRINTfile commands that do not have a specific STEP value.
- SImUdIV=VAL

Specifies how many times status information will be printed out during simulation. For example, SIMUDIv=10 causes a print out after each \(10^{\text {th }}\) of the simulation, for example each \(10^{\text {th }}\) of tstop. Status information recorded includes the elapsed CPU time, estimated total CPU time, percentage of simulation done, plus any data selected using the STAT option. Can also be used independently of stat. Cannot be used in conjunction with timediv. Default is 10 . Set simudiv to 0 to remove the print out.
- STAT=VAL

Used to set debug levels for simulation. Four values are allowed: \(0,1,2,3\).
0
Default. Specifies no statistics are to be recorded.
1
Reports newton/osr partitioning in the .chi file and to the terminal. Writes a trace of parameter and object updates in .chi \(\log\) file. Simulation time data is written to the .chi file when simudiv or timediv are used.
2
As level 1 plus: a node list is written to the .chi file.
3
As level 2 plus: parameter and object update tracing is also listed to the terminal (stdout). The number of rejected/accepted timesteps is reported when SImUDIv or timediv are used.
- NOSTATP

Disables the print out of parameter values when STAT option is set to a non-zero value (Stat is then used only for partitioning information).
- TIMEDIV=VAL

Works in conjunction with STAT. This option is equivalent to simudiv except Val now specifies a CPU time interval. Status information will be printed out after every VAL minutes of elapsed CPU time. This may significantly slow down simulation. Cannot be used in conjunction with sImudiv.
- tempcouk

By default, all the temperatures are plotted in Celsius in the binary output file (.wdb). Setting this option causes the temperatures to be plotted in Kelvin.
- VBCSAT=VAL

Default is 0 . Sets the 'region of work' that is displayed on the op table for BJT as follows:
```

if(VBC > VBCSAT)
if(VBE > 0) "SATURATION"
else "INVERSE"
else
if (VBE > O ) "ON"
else "OFF"

```
- vxprobe

Adding this option with . Probe v forces Eldo to dump ground and subcircuit node voltages to the output file.
- WRITE_ALTER_NETLIST

When specified, for each .ALTER, the altered netlist used by Eldo is written in the .chi file.

\section*{Optimizer Output Control Options}
- OPSELDO_ABSTRACT

Generates a summary table of simulations containing parameter and extract values for each run.
- OPSELDO_DETAIL=[NONE|ALL]

If this option is set to nONE, only the last run and the nominal run will be stored in generated files (. \(w d b, . a e x)\) and no other simulation information will be displayed. When set to ALL, simulation information for all runs will be stored. Default is NONE.
- OPSELDO_DISPLAY_GOALFITTING

Displays the intermediate goals when splitting DC measurements during optimization. Each .DATA point is optimized as an independent goal.
- OPSELDO_FORCE_GOALFITTING

Forces Eldo to split DC fitting extracts in independent goals even if data points are correctly ordered (as opposed to OPSELDo_nogoalfitting). It can also split AC fitting extracts.

Disables the splitting of DC measurements during optimization. By default, each .DATA point is optimized as an independent goal.
- OPSELDO_JWDB_RUN

Organizes the Waveform List of EZwave in a different way allowing easy access to results for different optimizer runs. This can also be specified using the -opseldo_jwdb_run flag when invoking Eldo.
The effect of the opseldo_Jwdb_run option can be seen in Figure 11-1; the image on the left is without the option, the image on the right is with the option specified.

Figure 11-1. OPSELDO_JWDB_RUN option effect

- OPSELDO_NETLIST

Generates a netlist modified from the original input file, which contains the optimized parameter values but also every parameter set under \#ifdef statements.
- OPSELDO_NO_DUPLICATE

When a . PARAMOPT is declared twice Eldo will generate both a warning and an error with this option specified. By default, double definition of .PARAMOPT is allowed with only warnings generated.
- OpSELDO_NOGOALFItTTNG

Disables the splitting of DC measurements during optimization. By default, each .DATA point is optimized as an independent goal only if they are not correctly ordered.
- OPSELDO_OUTER

Allows a reverse behavior of optimization and sweep simulations (.TEMP, .DATA or .STEP). A full optimization will be performed for each set of sweep parameters.
- OPSELDO_OUTPUT

This option controls results of optimization (Opsim or bisection method).
OPSELDO_OUTPUT=0
Print results in a simplified format: parameter name, goal, optimized value
OPSELDO_OUTPUT=1
Print results using simplified format (as for opseldo_output=0) and generate a .ops0 file using the same format.

OPSELDO_OUTPUT=2
Print results in a detailed format: parameter name, minimum value, maximum value, weight, goal, optimized value
OPSELDO_OUTPUT=3
Print results using detailed format (as for opSELDO_OUTPUT=2) and generate a .ops0 file using the same format.
- ReSet_MULTIPLE_RUN

This option is used internally by Eldo to disable multiple-run analyses (. Step, . TEMP). It is only used in the files generated by Eldo to replay some optimization runs. Parameters are assigned values and multiple-run analyses are disabled.

\section*{Caution}

The behavior cannot be predicted if this option is specified by the user instead of by Eldo.

\section*{File Generation Options}
- AEX[=0|1|2]

Forces Eldo to dump the results of .extract or .meas commands into a file filename.aex. The values are still also written into the .chi file. This is the default. See also option noasx.

\section*{AEX=0}

Equivalent to option nodex.

AEX=1
Equivalent to option \(\mathbf{A E X}\).
\(\mathbf{A E X}=2\)
Equivalent to option AEX with the header modified to report the version number of Eldo.

\section*{- ALIGNEXT}

Specifies that Eldo will write aligned . Extract results in the .aex file (aligned using space characters). By default the results are not aligned. Remember, the .aex file is only created if the option AEX is activated.
- ASCII=VAL

If VAL is set to 0 , the ASCII output file generation is terminated. If VAL is set to 1 , the ASCII output file is created. The default value is 1 . This option does not have the same meaning as the option "ASCII" on page 998.
- cou

Used to generate output in binary Cou format. This can also be specified using the invoke command -gwl cou.
- CSDF

Used to generate output in CSDF format. CSDF is the Common Simulation Data Format. This can also be specified using the invoke command -gwl csdf.
- DUMP_FILE_LIST

Generates a file containing all the files opened by Eldo (except temporary Eldo files) for a simulation. Useful for packaging an Eldo testcase. If a filename is not specified, then the netlist name is used with the extension .files_dump. If a relative path is specified then the file will be generated from the directory specified in -outpath.
The generated file contains all the absolute names of the opened files and is sorted by path and then by name (case ignored). Only one file is generated even if there are .alter statements or multiple netlists in the source file.
This option is equivalent to the -dump_file_list command-line flag of Eldo.
- FSDB

Used to generate output in FSDB format for nWave. This can also be specified using the invoke command -gwl fsdb.

\section*{- FSDB_SINGLE_FILE}

Removes the analysis name from the FSDB output filename and from the waveform hierarchy. By default, FSDB output files are named using the analysis, <netlist>.<analysis_name>.fsdb because they can only contain one analysis. The name of the analysis also appears in the waveform hierarchy like folders in JWDB.

If multiple analyses are performed in the netlist, the FSDB file will be replaced from one analysis to another.
- INFODEV=file_dev

Eldo will generate a file file_dev that contains all of the R/L/C/M/B/D/J device names with their corresponding parameter values evaluated.
- INFOMOD=file_mod

Eldo will generate a file file_mod that contains all of the .MODEL commands with their parameter values evaluated.
- ITRPRT

Forces Eldo to dump in the ASCII output table all the points which have been computed (internal time points), instead of those computed from the time interval specified in the .TRAN command. Note that with this option set, the ASCII output file can be huge.
- JwDB

Used to generate output in JWDB format (extension .wdb). This can also be specified using the invoke command -gwl jwdb. See also option nouwdb.
- NOAEX

Suppresses the AEX option and hence cancels the creation of filename.aex. The values are only written into the .chi file. See option aex.
- NOJWDB

Specifying this option will disable the generation of the output in JWDB format. This can also be specified using the -nojwdb flag when invoking Eldo. See also option JwDB.
- nocou

Suppresses the generation of the binary monitored results (.cou) file. See also option cou.
- noiticxname

Used to restore the full name display in the .iic file. (This was the default behavior in releases prior to v6.5.) By default, the saved simulation run file (.iic) format compresses the hierarchical names, in order to reduce the size of the file. With this option, the file produced can become very large when simulating large circuits with lots of hierarchy because the node names are stored flat.
- nockrstsave

By default, if the same file name appears in a . SAVE command and in a . RESTART command, and if conditions for reading and writing the file are not the same, then Eldo issues an error. This is in order to prevent Eldo unexpectedly overwriting restart files which take a long time to create. nockrstsave disables that check.
- noprobeop

When running Eldo in the ST mode, this will remove creation of the PROBEOP file.
- NSAFILE_FORMAT=COU|WDB|NONE

By default, the noise response of devices output by .OPTNOISE are merged into the NOISE folder of the.\(w d b\) file. Use this option to control the output generated. Set to cou for
backward compatiblity (pre-2009.2) behavior to create a separate <netlist>_nsa.cou file. Set to none to disable the creation of this file if you are only interested in the table inside the .chi file. Default is wDb.

\section*{- OUT_REDUCE}

Used to reduce the accuracy of output waveforms by performing a slope based comparison of output points. This is useful to reduce the number of points in case you have both constant (or slow varying) waves and varying waves in the same file. The comparison works by searching for groups of three points which are aligned. The middle point is ignored if the following condition is met:
```

|current_slope - previous_slope| <
OUT_ABSTOL + OUT_RELTOL × |current_slope|

```

Where OUT_ABSTOL and OUT_RELTOL are options which can also invoke the waveform reduction comparison.

As soon as this option is set, output waveforms are stored asynchronously that is, each wave will have it's own X values. Thus the size of the.\(w d b\) waveform database file may decrease or increase depending on the variations of waveforms. This option is useful if output waveforms contain constant signals, pulses, or slow varying signals. For example, power supplies which are constant require only two points at tstart and tstop.
- OUT_ABSTOL=value

Used to reduce the accuracy of output waveforms and set the absolute tolerance value.
Default is 1.0E-5. See OUT_REDUCE for details.
- out_reltol=value

Used to reduce the accuracy of output waveforms and set the relative tolerance value. Default is 1.0E-6. See OUT_REDUCE for details.

\section*{Caution}

Simulation time could increase when specifying options out_reduce, out_Abstol or out_reltol. They are not performance options.

\section*{- PROBE}

When -compat is set, then the Eldo .Probe command is emulated, that is, all node voltages are dumped in the binary output file (. \(w d b\) ). In order to have only those items specified in ..рцот/.probe to be dumped in the output file, add option probe.

\section*{- Probeop}

This option will be active only if . op is explicitly required. By default, . AC will not create the probeop file. The probeop option is used to write in a file the operating point information displayed in the chi file in a format easier to read for post-processors. If probeor is set, the name of the file is probeop.

\section*{- PROBEOP2}

Eldo will generate two files: <circuit>.op \(\langle x\rangle\) and <circuit>.mapop. For <circuit>.op \(\langle x\rangle\), \(x\) is the index of the run, it contains OP information for the current run. This file is an ASCII file. The first line of the file contains the ALTER index (if any), the MC index (if any), as well as the temperature values and the step value if . STEP is specified. The content of this file is similar to that created when option Probeop is used, but some additional information is dumped: temperature, node information, and current out of X leaf-instances (leaf-cells are instances which do not call any other X instances). For <circuit>.mapop, each line contains an index, corresponding to the index of the .op file, followed by the same information which can be found on the first line of the corresponding .op file. This mapping file facilitates the search of a specific configuration, rather than having to visit the first line of each .op file.
- PROBEOPX

Force Eldo, during the OP analysis, to display the current which flows in each pin of each subcircuit X instance. This command will be active only if .OP is explicitly required.
- PSF

Used to generate output in Cadence format. This can also be specified using the command line flag -gwl psf. The list of directories and files created by the PSF format will be printed at the end of the .chi file. For example:
```

==== Files and directories created by the PSF output format ====
/home/user/test/analysisInst
/home/user/timeSweep
/home/user/logFile
/home/user/test/variables_file

```

\section*{- PSF_NODEVICE_NOISE}

Disables the saving of the individual noise contributions per device, and instructs Eldo to keep only total noise in the PSF noise file. This provides backward compatibility with versions of Eldo prior to v6.10_1. The noise contributions of all devices are saved in a PSF file named noise by default.
- PSF_SCALARDC [=0|1]

Selects saving DC values in scalar PSF format or sweep PSF format. PSF_SCALARDC=1 selects scalar PSF format output. This is automatically selected if option PSF_WRITE_ALL is specified. PSF_SCALARDC=0 is the default for backward compatibility.
- PSF_VERSION=1|2

Selects between two versions of the PSF output module in Eldo. PSF_version=2 (default) selects the module introduced in Eldo v6.9; PSF_VERSION=1 selects the output module available prior to Eldo v6.9. (Both modules will output the same PSF output format: PSFversion 1.00.) With the newer output module selected, extended options PSF_FULLNAME and psf_All_files become available. By default, Eldo will not enable these two options to stay compatible with Artist Link. The newer module makes it possible to generate files larger than 2 Gb for TRAN and TSST analysis.

\section*{- PSF_FULLNAME}

Instructs Eldo to save all waveforms in the output file using their complete names. In default mode, \(\mathrm{V}(\mathrm{OUT})\) is saved as OUT. Using this option allows to save phase noise, harmonic waveforms, and noise circles. Output files keep the usual PSF naming convention: timedomain files are called timeSweep and frequency-domain files are called frequencySweep. There is only one file per analysis domain.
- PSF_ALL_FILES

Alias of PSF_WRITE_ALL.
- PSF_WRITE_ALL

This option overrides the rule of creating one file per analysis domain (usually timeSweep and frequencySweep). It instructs Eldo to use the exact analysis name for the output file. For example .SSTNOISE analysis creates a "noise" file by default. With this option, the output file will be named sstnoiseSweep. It also enables the saving of all waveforms in the output file (using . H() extension for RF outputs), and the activation of PSF_SCALARDC option to save the DC output values in scalar PSF format.
- PSFASCII

Used to generate PSF format data in ASCII. This can also be specified using the invoke command -gwl psfascii.
- SAVETIME=VAL

Creates a .sav file which saves the context of a simulation every val hours of CPU time used in a transient analysis. If the system crashes during a run, the simulation may be restarted from the last saving time.
- WDF

Used to generate output in FSDB format for nWave. This can also be specified using the invoke command -gwl fsdb.

\section*{Mathematical Algorithm Options}

For more details on these options, please refer to the Speed and Accuracy and Integral Equation Method (IEM) chapters.
- TRAP

Resets the integration method to "Trapezoidal" from "Backward Euler." Useful in interactive mode only. Related parameters: sмоотн.

\section*{- SMOOTH}

When the "Trapezoidal" integration method is used, oscillation may occur on some output curves. This Sмоотн option forces Eldo to display at the mid-point of the computed time intervals, this operation acts as a filter and oscillations due to TRAP are removed.
- BE

Forces "Backward Euler" integration to be used. "Trapezoidal" integration is used by default.
- GEAR

Forces "Gear" integration to be used. Trapezoidal integration is used by default. Related parameters: maxord, chgtol, ngtol, fluxtol, reltrunc. Take care with the gear algorithms as you may potentially miss some oscillations in circuits.
- GNODE

Assists DC convergence for .RAMP DC and option GRAMP. GNODe is the conductance which is applied between each node and ground. The value input by the user is the conductance value to be used as the first RAMP point. Eldo will reduce the value down to 0 for the final RAMP point, when conducting a RAMP analysis.
- METHOD=GEAR

See the option GEAR above (used only for compatibility with SPICE).
- maxord=VAL

Used in conjunction with option GeAR. Specifies the maximum order of the Gear integration method and must be in the range 1 to 6 . The value 1 is equivalent to the \(\mathbf{B E}\) option. Default value is 2 .
- newton

Forces Eldo to use only one Newton block on the design. This is the default algorithm.
- nodefnewton

Forces Eldo to use OSR by default, instead of Newton. See option newton.
- IEM

Forces Eldo to use only one IEM block on the design.
- BLOCKS=NEWTON

Forces Eldo to use OSR on the whole circuit and Newton-Raphson algorithm on tightly coupled sub-blocks. If the whole circuit was tightly coupled, then Eldo will automatically switch to newton, after issuing a message.
- BLOCKS=IEM

Forces Eldo to use OSR on the whole circuit and IEM algorithm on tightly coupled subblocks. If the whole circuit was tightly coupled, then Eldo will automatically switch to IEM, after issuing a message.
- analog

Forces Eldo to create only one Newton block for the whole circuit and adjusts EPS to a maximum value of \(1.0 \times 10^{-4}\) in order to achieve higher accuracy results.

\section*{- DIGITAL}

When the OSR algorithm is selected, this forces nodes which are not in analog blocks and which are connected to MOSFET, grounded capacitors, current sources or floating capacitors of less than CAPANW to be solved by OSR, all other nodes being treated by Newton-Raphson. This option is useful for large MOS circuits with extracted parasitic coupling capacitances.
- OSR

Forces Eldo to use the OSR (One Step Relaxation) iteration technique whenever possible, that is, for MOS loosely coupled circuits. Related parameters: dIgItal, CAPANw.
- NORMOS

This option allows the removal of access resistances in analog blocks if low precision simulation is required. For circuit blocks simulated using OSR at a relatively low precision level, MOS access resistances are not treated as separate elements. Their effect is taken into account during MOS model evaluation in an approximate manner. It is sometimes possible for analog blocks simulated using either Newton Raphson or IEM to have these devices (that is, MOS transistor with an approximate access resistance effect). This happens for example when the circuit is dynamically re partitioned during simulation for convergence problems. Analog blocks (solved by Newton or IEM) should maintain a minimum level of precision hence access resistors should be created as new elements.

Hence, specifying normos selects the mechanism that allows dynamic creation/removal of these devices depending on the algorithm used: removal for OSR and creation for both Newton and IEM.
- PSTRAN

Forces Eldo to use the PSTRAN (PSeudo TRANsient) algorithm prior to any other convergence aid. This algorithm is one of the DC convergence algorithms that are automatically used by Eldo when the standard DC algorithm fails to converge.
- DPTRAN

Forces Eldo to use the DPTRAN algorithm prior to any other convergence aid. This algorithm is one of the DC convergence algorithms that are automatically used by Eldo when the standard DC algorithm fails to converge.
- NODCPART

Do not insist on DC partitioning in DC analysis. In case of convergence difficulties, immediately go to the convergence aid algorithm.
- DCPART=VAL

Here, val is the number of time partitions that will occur, the default is 5 . DCPART=0 is equivalent to option nodcrart.
- CSHUNT

Add a capacitance between each node and ground. Default is 0 . This can be used to eliminate oscillation problems caused by numerical noise or high frequency oscillation.

\section*{- GSHUNT}

Add a conductance between each node and ground. Default is 0 . This can be used to eliminate oscillation problems caused by numerical noise or high frequency oscillation.

\section*{Mixed-Mode Options}
- D2DMVL9BIT

Enables direct connection between HDL-A ports of type BIT with mixed-mode nodes connected to Eldo via convertors of type MVL9 (or std_logic).
Further information can be found in ".A2D" on page 528 or ".D2A" on page 577.
- DEFA2D=model_name

Eldo will automatically insert an implicit A2D convertor when needed. Without this option specified, it is normally necessary to specify an explicit A2D between ANALOG nodes and HDL-A ports.

Further information can be found under "Option DEFA2D" on page 536.
- DEFD2A=model_name

Eldo will automatically insert an implicit D2A convertor when needed. Without this option specified, it is normally necessary to specify an explicit D2A between ANALOG nodes and HDL-A ports.
Further information can be found under "Option DEFD2A" on page 584.
- defconvmsg

Forces Eldo to print out in ASCII output files the convertor information related to the .A2D and .D2A which are added when options DEFA2D and DEFD2A are specified.

\section*{- DYND2ALOG}

Enables the threshold voltages VTHI and VTLO to be calculated dynamically for digital macromodels using actual values of the high and low bias. The bias values, VHI and VLO are computed using two extra pins defined by the user in the digital model instance. The value specified on the first pin provides the high voltage digital output value (VHI) and the value specified on the second pin provides the low voltage digital output value (VLO). The two extra pins are placed after the list of regular pins and before the model name in the model instance syntax, see "Digital Macromodels" on page 447 for more information. This option must be placed at the top of the design, just after the title line.
The active VTHI and VTLO threshold values are also computed dynamically using the following equations:
```

VTHI_ACTIVE = VLO + VTHI*DV
VTLO_ACTIVE = VLO + VTLO*DV

```

VTHI and VTLO are the values specified in the .MODEL command defining the digital macromodel or in the macromodel instance, VLO is the low output voltage value given on
the second extra pin defined by the user, and DV is the voltage difference given by VHI VLO.
- DYND2ALOG2

Specifying this option activates the already existing option DYND2ALOG for dynamically calculating threshold values of digital macromodels, and also changes the way the thresholds are detected.

For the detection of the rising edge, and in DYnd2ALOG2 mode, Eldo checks for V > VTH and VLAST <= VTH_LAST where V and VTH are the voltage and the threshold value at the current time point, and VLAST and VTH_LAST the same entities but at the previous time step.

If dynd2alog is set, Eldo will check for: for V > VTH and VLAST <= VTH, which is also the formula used in case none of the options DYND2ALOG2 and DYND2ALOG are set.

This change of the expression has a major impact in the threshold detection for the case the pin which is used to carry the voltage used as the threshold value is also an input pin: the output of the small circuit will change depending on the option set.
- MIXEDSTEP=FREE | LOCKED

Used for controlling time-step synchronization between Eldo and a digital solver (ADVance MS or Verilog-XL). This option can take two values: free or locked. Default is FREE.

When mixedstep is free, simulation is usually faster, but may fail on some rare cases with a message inviting the user to re-run the simulation with mixedstep=Locked.

When mixedstep is Locked, the analog kernel will stop on each digital event even if these digital events have no immediate impact on the analog side. This mode of simulation is very robust, but is usually slower except in cases where most of the digital events have an immediate impact on the analog side.
- PARTVDD=node_name

Instructs Eldo/ADMS that the specified node can be accepted as a boundary node between ADMS (Eldo) and ADiT even if it does not conform to the partitioning rules. Using this option can significantly reduce the simulation time, so must be used with caution.
- PARTVDD_AMS_ALL

Instructs ADMS to put the option PARTVDD on all nodes connected to a VHDL-AMS model. The partitioner will consider all the nodes connected to a VHDL-AMS model to be low coupling nodes for partitioning. This will lead to more devices being simulated by ADiT. A list of the nodes that the option has been set on will be displayed. Using this option can significantly reduce the simulation time, so must be used with caution.
- PARTGATE_AMS_ALL

Forces the partitioner to cut on Questa ADMS ports. This option is similar to
PARTVDD_AMS_ALL but has the opposite behavior. That is, the option instructs ADiT that all
nodes connected to VHDL-AMS models can be accepted as boundary nodes between ADiT and Eldo, even if they do not conform to the partitioning rules.
- FS_PARTITIONING=level

Specifies different algorithms to be used for the partitioning rules used by Eldo and ADiT in white-box mode. There are six levels of partitioning, numbered from 5 (most partitioning) to 0 (least partitioning). The default is 4 .

The partitioner defines the objects that will be simulated by Eldo and ADiT. The basic principle of this partitioner is to modify the partitioning made by the user in order to reduce, as much as possible, the coupling level between partitions.
Please refer to Partitioning Options in the Questa ADMS User's Manual for further information.
- FS_PARTITION_DEBUG[=val]

Causes Eldo (ADMS) to display the first defined number of devices which will be simulated on the Eldo side while they are partitioned inside the netlist (using . OPTION or . PART commands) to be simulated by fast SPICE (ADiT). The reason why the device will be simulated with Eldo is also reported. If no value is specified, the default is 10 .
Please refer to Partitioning Options in the Questa ADMS User's Manual for further information.
- FS_SOLVE_AMS_NODES

Instructs ADMS to force all nodes directly connected to VHDL-AMS nodes to be solved by ADiT.
- NO_FS_VA

Forces Verilog-A models to be sent to Eldo instead of ADiT.
- VAMODEL=mod_name

Used in conjunction with the .hDL command. See ".HDL" on page 678 for further information. The Verilog-A module name specified with this option has higher priority than a subcircuit of the same name when both exist. Only one module name can be specified on each vamodel option. Multiple names require multiple specifications. Same behavior as -vamodel flag, see also "-vamodel <mod_name1> -vamodel <mod_name2> . . ." on page 56.
- SPMODEL=subckt_name

Used in conjunction with the .hDL command. See ".HDL" on page 678 for further information. The subcircuit name specified with this option has higher priority than a Verilog-A module of the same name when both exist. Only one subcircuit name can be specified on each SPMODEL option. Multiple names require multiple specifications. Same behavior as -spmodel flag, see also "-spmodel <subckt_name1> -spmodel <subckt_name2> . . ." on page 54.
- VAOPTS=options_string

Used in conjunction with the .hDL command. See ".HDL" on page 678 for further information. Specifies options for the Verilog-A compiler. For example:
```

.option vaopts="-lrm10"
.verilog file.va

```

The Verilog-A compiler will be called with the - lrm10 option.

\section*{Other Options}
- Cteprec

With this option, fundamental physical constants are as follows (SI units):
Free space permittivity \((\) epso \()=8.854187817 \times 10^{-12}\);
Boltzmann constant \((\) boltz \()=1.38065812 \times 10^{-23}\).
Electron charge \((\) charge \()=1.6021773349 \times 10^{-19}\);
Twice pi \((\) twopi \()=4.0 \times \operatorname{asin}(1.0)\);
By default, Spice2G6 values are used:
epso \(=8.854214871 \times 10^{-12}\);
boltz \(=1.3806226 \times 10^{-23}\);
charge \(=1.6021918 \times 10^{-19}\);
twopi \(=6.283185308\);
- DCLOG=VAL

When Eldo is used with a circuit containing digital gates, a DC analysis is run at first, then the output of the digital gates is updated, and then another DC analysis is run, that is, there are relaxations between DIGITAL and Eldo. There are DCLOG relaxations. Default is 1 .
- EPSO=VAL

Allows overwriting of the EPSO value.
- MAXNODEORD

If number of nodes in the netlist is less than maxnodeord, then in the op node table, node names are listed by alphabetic order. If the number of nodes exceeds maxnodeord, node names are listed in the order that Eldo has chosen. Default is 300 .
- NODUPINSTERR

When specified in conjunction with the stver flag/option, will change ERROR 838 into WARNING 204. This option is ignored if not specified with the stver flag/option.
- noeldoswitch

When specified with the -compat flag/option, it informs Eldo that devices beginning with an \(S\) are not switches (Eldo default) but S-parameter block instantiations. This option is ignored if not specified with the compat flag/option.
- NOINIT

Prior to an AC or Transient run with UIC active (that is, no DC analysis to be performed), Eldo performs a logical initialization, unless noinit is defined.

The concept behind this 'logical initialization' is as follows: consider a PMOS element, with 0 V imposed on the gate (via an independent voltage source for instance), and the Source connected to power supply VDD. Then, if Drain has not been initialized, Eldo would initialize its value to VDD, and the value will propagate as far as it can. This algorithm would correctly initialize CMOS designs.
- NOFNSIEM

The Integral Equation Method (IEM) is used in Transient Analysis to solve FNS functions. Specifying nofnsiem reverts to the implementation based on state variables.
- SEARCH=path1 [\{:path2\}]

When Eldo does not find a subcircuit called <name> or a model definition called <name>, it will look for the file path1/<name>.inc. The name is converted into lowercase before searching, and, if more than one SEARCH option is given, Eldo will search all the directories in the path specified by the user in the order that they appear inside the input file.

If more than one path is specified it will search all of the paths. Each path name must be separated by a colon. There is no limit to the number of paths that can be specified.
This has the same effect as using -searchpath in the Eldo instantiation. See "Running Eldo from the Command Line" on page 41.
- VAMAXEXP=val

In Verilog-A, the argument of any exponential is limited to vamaxexp. Default is 80.0. This is to limit \(\exp\) (value) when value is too large.
- zChar=VAL

Characteristic impedance of the circuit. Default is 50 Ohms.

\title{
Chapter 12 Transient Noise Analysis
}

\section*{Introduction to Transient Noise Analysis}

In most analog design applications, knowledge of noise levels generated by the circuit is of great importance. In all traditional SPICE-like simulators, noise computation is only available in AC analysis. In this case the circuit is assumed to have a fixed bias (DC operating point), and noise simulation can only be applied to circuits working under small signal conditions. For this reason, many applications cannot be simulated and their noise performance is unknown until physical measurement is possible on the manufactured design. The only other method available to obtain this important information is to perform tedious hand calculations (when possible).

Eldo provides a solution to this noise analysis problem:

\section*{Noise Simulation During Transient Analysis}

Transient noise simulation can be applied to all types of circuit without restriction. To perform transient noise analysis, physical noise of electrical devices is emulated by time dependent current sources. The frequency characteristics of these sources are referred to the noise models of the noisy components. The method used is simple, fast and does not disturb the simulated behavior of the circuit because the noise signals introduced are continuous and fully deterministic.

Simulation results from transient noise analysis include:
- Transient response of the circuit, as generated by a pure transient analysis.
- Transient response with the added noise generated by the circuit (plotted as an oscillogram of experimental measurements).
- The RMS value of the noise versus time which gives the accuracy of the ideal transient response.

To compute the RMS value of the generated noise, Eldo performs a normal transient analysis of the circuit, plus \(\boldsymbol{N}\) transient simulations which include noise sources within the noisy devices. The RMS value of noise is computed at each time-step as follows:
\[
R M S(t)=\sqrt{\frac{1}{N} \sum_{i=1}^{N}\left(V_{i}(t)-V_{o}(t)\right)^{2}}
\]

Where \(V_{\boldsymbol{o}}(\boldsymbol{t})\) represents the noiseless transient response of the circuit, and \(\boldsymbol{V}_{\boldsymbol{i}}(\boldsymbol{t})\) is the \(\boldsymbol{i}^{\text {th }}\) transient response of the circuit including the noise sources; \(N\) is the number of noise simulations performed.

To perform transient noise analysis, Eldo adds a noise contribution to the same components as in AC noise analysis (R, M, B, J, D, see below). Moreover, an additional noise model, connected with the Switch macromodel (S), has been introduced. It is therefore possible to simulate noise in switched capacitor circuits (see "Example 2Switched Capacitor Filter" on page 1031).

Figure 12-1. Circuit Components with their Added Noise Sources

(1) Please refer to the noise models in the respective sections of the Device Models chapter.

\section*{.NOISETRAN Command}
.NOISETRAN FMIN=VAL FMAX=VAL NBRUN=VAL [OPTIONS]
This command is used to control the transient noise analysis of a circuit and must be used in conjunction with a transient analysis (.TRAN).

\section*{Parameters}
- FMIN, FMAX

Define the range of the noise frequency band (same function as fstart and fstor in AC noise analysis).

\section*{Note}

FMIN and FMAX define the frequency band of the noise sources. This frequency range may sometimes not correspond to the noise frequency band at the output of the circuit. For instance, the band (FMIN, FMAX) does not correspond to the output noise frequency band in the case of filters, oscillators and mixers that exhibit frequency conversion.
- NBRUN

Defines the number of noise simulations to perform (those which include the noise sources). This parameter defines the accuracy of the noise analysis.

\section*{Caution}

Care must be taken when setting the nBRUN parameter as it strongly influences the CPU time used by the simulation.
- OPTIONS

Other options are available for more advanced and more efficient use of the command.

\section*{1 Please refer to ".NOISETRAN" on page 747 for more details.}

Two methods exist to generate transient noise signals. One uses a sum of sine waves with random phases. It is activated when FMIN is not zero. The second method, only activated when FMIN=0, uses gaussian random variables to generate noise sources. A noise source, with given frequency characteristics, will produce two different noise signals depending on the method used to generate them. These signals will have different instantaneous values but will have the same power and same frequency content.

During the transient noise analysis, Eldo generates noise sources in the time domain for each noisy component. These noise sources are generated as a sum of nBF sinusoids distributed between FMIN and FMAX. It means that the generated noise sources have a spectrum of discrete points and the energy of the noise sources is localized in a limited number of frequency points. When a frequency band is wide the corresponding generated noise source may have a poor frequency resolution.

Consequently, an alternative algorithm was developed to generate the noise sources, leading to a continuous spectrum in the frequency band zero to FMAX. This algorithm is approximately twice as fast and with more accurate results. However, it cannot generate a noise source with a frequency band beginning at a value of FMIN other than zero. This algorithm is automatically activated by specifying FMIN as zero. When FMIN is different from zero, the method using sinusoids is then used. Both methods can work together, one for some components, the other method for different noisy devices.

The alternative method (when \(\operatorname{FMIN}=0\) ) is used to generate flicker noise and white noise sources (thermal and shot noise). It is not possible to have a flicker noise source with a frequency band starting from zero, therefore the generated flicker noise source will have a white spectrum from zero to F1 and a flicker noise spectrum from F1 to FMAx. The frequency F1 is calculated from the transient simulation duration: \(\mathrm{F} 1=1 /\) TSTOP .

\section*{Example 1—High-rate Particle Detector}

Figure 12-2. High-rate Particle Detector Circuit


This circuit was designed at CERN and is used in high-rate particle detection. It comprises a front-end pre-amplifier and an analog memory port. Performance analysis of the complete circuit is given in the following sections. Transient simulations have been performed and noise characteristics investigated. The netlist for the circuit, describing the analysis performed, can be found after the simulation results.

\section*{Description of the Particle Detector Behavior}

The pre-amplifier has a rise time of less than 20 ns and a large fall time constant compared to the rise time. Therefore, for this application it can be considered as an integrator. The function of the analog memory port is signal storage and noise shaping. It takes successive samples of the signal into the different feedback capacitors. The complete system of analog memories acts as a
charge sampler and is equivalent, from a signal processing point of view, to a discrete differentiator.

Shown below is the signal at the input, the voltage at the amplifier output and the signal at the output of the complete system. The simulation was performed for an input charge of 2.5 fC across a 5 pF input capacitor and with a 15 ns clock period.

The clock of the analog memory port is synchronized with the input signal in order to store the maximum amount of charge in the first feedback capacitor. We can note that most of the charge is deposited in one storage capacitor within the 15 ns clock period.

Figure 12-3. Simulation Results—Input \& Output Signals


\section*{Analysis of the Noise Performance}

The resolution of this detection system is a function of the noise generated by the circuit. It is therefore the major performance criterion of the device.

The noise performance of the complete circuit strongly depends on the performance of the preamplifier. The analog memory port does not generate noise, it only shapes the noise generated by the amplifier.

A number of transient noise simulations were performed on the complete circuit.
Figure 12-4. Noise at Amplifier O/P


Figure 12-4 shows the results of several transient simulation runs including noise sources, with different initial conditions and the RMS value of the noise at the amplifier output calculated from the different runs described above.

\section*{Note}

The RMS value of the noise increases with time and the Signal to Noise Ratio is limited by the low frequency noise components.

Figure 12-5. Noise at Analog Memory O/P


Figure 12-5 shows the curves related to the different runs with the noise sources, the signal at the output of the complete circuit, and the RMS value of the corresponding noise.

\section*{Note}

The effect of the analog memories on the noise behavior acts as a Correlated Double Sampling, meaning that output noise is reset at each period of the clock.

For this type of circuit, the noise performance is expressed in terms of Equivalent Noise Charge referred on the input (ENC):
\[
E N C=\frac{\text { Noise }}{\text { Signal }} \text { Qin }
\]

Where Noise is the RMS noise value at the output (extracted from the figure above), Signal is the signal at the output and Qin is the charge injected across the input capacitor (in e \({ }^{-}\)). In this case, the \(\boldsymbol{E N C}\) is about 2000e \({ }^{-}\)across Cin (Noise \(=0.9 \mathrm{mV}\), Signal \(=7 \mathrm{mV}\), Qin=2.5 fC). This circuit has been manufactured and experimental measurements match the simulation results very closely.

\section*{Netlist for Example 1}
```

********* MOS MODELS *************
.model nmost nmos level=3 vto=0.75 gamma=0.4 phi=0.457

+ nsub=2.0e15 theta=0.05 ld=0.2e-06 xj=0.3e-6 tox=32.5e-9
+ delta=0.5 uo=700 rsh=37 eta=0.03 cj=20e-5 cjsw=3.5e-10
+ cgso=2.1e-10 cgdo=2.1e-10 mj=0.6 mjsw=0.4 cgbo=8.3e-10
+ pb=0.6 vmax=100e3 kappa=0.48 kf=16.8e-28 nfs=1e10
.model pmost pmos level=3 vto=-0.75 gamma=0.4 phi=0.6
+ nsub=1.0e16 theta=0.14 ld=0.3e-06 xj=0.4e-6 tox=32.5e-9
+ delta=1.5 uo=220 rsh=85 eta=0.08 cj=33e-5 cjsw=3.5e-10
+ cgso=3.1e-10 cgdo=3.1e-10 mj=0.42 mjsw=0.3 cgbo=8.3e-10
+ pb=0.6 vmax=206e3 kappa=15 kf=7.04e-29 nfs=1e10
****** SWITCH MACROMODEL *******
.MODEL swi NSW vh=0.1 vth=2 ron=1 c1=0 c2=0 crec=0
****** CIRCUIT DESCRIPTION *******
**** THE BIAS
Ipol vdd 1 60u
mn1 1 1 vss vss nmost w=35.5u l=5u
mnt1 2 1 vss vss nmost w=35.5u l=5u
mpt1 2 2 vdd vdd pmost w=70u l=5u
mnb2 pb 1 vss vss nmost w=35.5u l=5u
mpb2 nb 2 vdd vdd pmost w=70u l=5u
mnb1 nb nb 0 vss nmost w=540u l=1.5u
mpb1 pb pb 0 vdd pmost w=1080u l=1.5u
**** THE PRE-AMPLIFIER
mnil ul nb in vss nmost w=540u l=1.5u AD=+3.375E-09
+ AS=+3.6E-09 PD=+1.635E-03 PS=+1.744E-03
mpil d1 pb in vdd pmost w=1080u l=1.5u AD=+3.375E-09
+ AS=+3.6E-09 PD=+1.635E-03 PS=+1.744E-03
mni2 d1 dl vss vss nmost w=35.5u l=5u AD=+9.0E-11
+ AS=+1.79E-10 PD=+5.0E-05 PS=+9.3E-05
mpi2 ul ul vdd vdd pmost w=70u l=5u AD=+9.0E-11
+ AS=+1.79E-10 PD=+5.0E-05 PS=+9.3E-05
mno1 out1 d1 vss vss nmost w=35.5u l=5u AD=+9.0E-11
+ AS=+1.79E-10 PD=+5.0E-05 PS=+9.3E-05
mpo1 out1 ul vdd vdd pmost w=70u l=5u AD=+9.0E-11
+ AS=+1.79E-10 PD=+5.0E-05 PS=+9.3E-05
Cin inin in 5pf
Rfb in out1 100meg
Cout out1 0 .2pf
Vdd vdd 0 3V
Vss vss 0 -3V
**** ANALOG MEMORY PORT
Coe1 out1 oe1 0.4pF
S1 phil oe1 s1 swi
Sr1 phi3 s1 out swi
Cfb1 s1 out 0.4pF ic=0
Vphil phi1 0 pulse(-5 5 .1n .1n .1n 15n 45.6n)
S2 phi2 oe1 s2 swi
Sr2 phi1 s2 out swi
Cfb2 s2 out 0.4pF ic=0
Vphi2 phi2 0 pulse(-5 5 15.3n .1n .1n 15n 45.6n)
S3 phi3 oe1 s3 swi
Sr3 phi2 s3 out swi
Cfb3 s3 out 0.4pF ic=0
Vphi3 phi3 0 pulse(-5 5 30.5n .1n .1n 15n 45.6n)

```
```

**OTA definition**
Gamp 0 out 0 oe1 .002
Ramp out 0 0.5Meg
Camp out 0 1pF
Cpip oe1 0 1pF
Ritg out oel 1g
.ic v(oe1)=0 v(s1)=0 v(s2)=0 v(s3)=0 v(out)=0
**** TRANSIENT NOISE SIMULATION
Vin inin 0 pwl(0 0 90n 0 90.1n 0.3mv 600n 0.3mv)
.tran 200n 200n
.noisetran fmin=100k fmax=100meg nbrun=20
.plot tran v(in)
.plot tran v(out1)
.plot tran v(out)
**** AC ANALYSIS OF THE AMPLIFIER
Vin in 0 dc 0 ac 1
.ac dec 10 100k 100meg
.noise V(out1) Vin 10
.plot ac vdb(out1)
.plot noise inoise onoise
.option thermal_noise=2
.end

```

\section*{Example 2—Switched Capacitor Filter}

Figure 12-6. Switched Capacitor Filter Circuit Schematic


This second example, shown above, is a 6th order switched capacitor bandpass filter used in telecommunications applications. Complete simulation results of the circuit and its noise performance are given in this section. To increase simulation speed, modeling is implemented at
a macromodel level rather than transistor level. The Eldo macromodels SWITCH and OPA are used. We will first describe the macromodels used and simulation results follow thereafter. Finally the netlist describing the simulation conditions is listed after the simulation results.

\section*{Characterization of the Amplifier}

The structure of the amplifier is a classical folded cascade. AC and transient simulations have been performed at a transistor level in order to determine the macromodel parameters of the circuit shown below:

Figure 12-7. Amplifier Schematic


A subcircuit composed of an OPA1 macromodel, and a voltage source representing the equivalent noise referred at the input, is used for the simulation of the complete circuit.

Figure 12-8. AC \& Noise Simulation Results of Amplifier


Figure 12-9. AC \& Noise Simulation of Amplifier Macromodel


The dominant pole of the amplifier is defined by the output impedance and load capacitance of the amplifier. Comparison of simulation results between the amplifier and its macromodel are shown in Figure 12-8 and Figure 12-9.

\section*{Netlist Used for the Amplifier Simulations}

\section*{AOP Analysis at Transistor Level}
```

AOP ANALYSIS
*** AOP Analysis at transistor level
.GLOBAL VDD VSS
.MODEL MN NMOS NIV=6 EOX=200E-10 MU0=520 DPHIF=0.8 DW=1.0E-6

+ DL=0.1E-6 VT0=0.75 KB=0.62 REC=0.1E-6 TG=0.08 VL=1.0E5
+GL=0.5E-6 KL=0.3E-6 KW=0.2E-6 DINF=0.3 GW=0.4E-6
+ LDIF=3.3E-6 CDIFSO=1.4E-4 CDIFPO=8E-10 VE=20E4 LMIN=1.2E-6
+ WMIN=3.4E-6 RSH=525 AF=1.33 Kf=2.7e-26
.MODEL MP PMOS NIV=6 EOX=200E-10 MU0=190 DPHIF=0.8 DW=1.0E-6
+ DL=0.3E-6 VT0=-0.8 KB=0.36 REC=0.1E-6 TG=0.13 VL=2E5
+GL=0.34E-6 KL=0.2E-6 KW=0.4E-6 DINF=0.12 GW=0.22E-6
+ LDIF=3.3E-6 CDIFSO=3.2E-4 CDIFP0=8E-10 VE=10E4 LMIN=1.4E-6
+WMIN=3.4E-6 RSH=1225 AF=0.89 KF=2e-29

```
```

.SUBCKT BIAS VB VB1 VB2 VB3
M1 VSS VB 4 VSS MN L=4.00U W=66.00U
M3 VSS VB VB VSS MN L=4.00U W=66.00U
M5 VB1 VB1 VSS VSS MN L=4.00U W=37.00U
M6 VB1 VB3 VB3 VSS MN L=8.00U W=144.60U
M9 VB3 VB3 8 8 MP L=1.40U W=97.20U
M11 4 4 VB2 VB2 MP L=4.00U W=241.00U
M15 VDD VB2 8 VDD MP L=3.00U W=96.40U
M17 VDD VB2 VB2 VDD MP L=3.00U W=96.40U
C19 VSS VB3 6.32179E00PF
C20 VSS VB2 6.32179E00PF
C21 VB1 VSS 6.32179E00PF
.ENDS
.SUBCKT OPAMP AOUT INP INN VB1 VB2 VB3
M1 VSS 13 11 VSS MN L=10.00U W=194.40U
M5 VSS VB1 12 VSS MN L=4.00U W=118.00U
M7 3 INP 12 VSS MN L=1.20U W=669.00U
M17 4 INN 12 VSS MN L=1.20U W=669.00U
M27 VSS 13 13 VSS MN L=10.00U W=194.40U
M31 13 14 14 VSS MN L=1.50U W=25.60U
M35 AOUT 14 11 VSS MN L=1.50U W=25.60U
M39 3 VB2 VDD VDD MP L=2.00U W=178.00U
M43 4 VB2 VDD VDD MP L=2.00U W=178.00U
M47 3 VB3 14 VDD MP L=1.40U W=194.80U
M51 4 VB3 AOUT VDD MP L=1.40U W=194.80U
.ENDS
***
vvdd vdd 0 2.5
vvss vss 0 -2.5
Xpol vb vb1 vb2 vb3 bias
Xaop s inp inn vb1 vb2 vb3 opamp
Rcha vdd vb 50k
Ccha s 0 50p
vinn inn 0 ac 1
vinp inp 0 0
.ac dec 10 1 10meg
.noise v(s) vinn 10
.plot noise onoise inoise
.plot ac vdb(s)
.option flicker_noise=1
.end

```

\section*{AOP Analysis at Macromodel Level}
```

********************************************
*** AOP analysis at macromodel level
.MODEL AMP OPA LEVEL=1 VOFF=0 IMAX=200UA

+ CIN=1.OE-12 RS=1Meg
+ GAIN=3500 FNDP=150Meg
+ VSAT=2.5 CMRR=-100db
. subckt opamp o1 o2 i1 i2
opax e1 i2 o1 o2 AMP
Vinoi e1 il noise 7.86e-18 4.29e-14 1.33
. ends

```
```

Xaop s 0 0 inn opamp
Ccha s 0 50p
vinn inn 0 ac 1
.ac dec 10 1 10meg
.noise v(s) vinn 10
.plot noise onoise inoise
.plot ac vdb(s)
.end

```

\section*{Switch Noise Model}

Instead of MOS transistors, a switch macromodel is used to perform the complete circuit simulations. To compute transient noise simulations, noise sources have been added to the switches. We have considered that a switch only generates thermal noise. A current source has been included between the source and the drain and its Power Spectral Density is a function of \(\boldsymbol{R}_{\boldsymbol{o}}\), as follows:
\[
S_{1}=\frac{4 k T}{R_{o n}}
\]

\section*{Simulation Results of the Complete Circuit}

Transient simulation results are shown below. In Figure 12-10 the first curve represents the impulse response of the circuit. The second curve represents the RMS value of noise generated at the output of the filter in the frequency band \((1 \mathrm{~Hz}, 50 \mathrm{kHz})\). We can see that this result is about 5 mV . This has been obtained by performing about 20 runs including noise sources. This curve would be smoother if more runs had been performed. Figure 12-11 shows the Fourier transform of the circuit output; it therefore represents the frequency response of the filter.

Figure 12-10. Simulation Results of the Filter


Figure 12-11. Frequency Response of the Filter


\section*{Netlist for Example 2}
```

* 6TH ORDER BAND-PASS FILTER *
.GLOBAL VDD VSS
VVDD VDD 0 2.5
VVSS VSS 0 -2.5
.MODEL AMP OPA LEVEL=1 VOFF=0 IMAX=200UA CIN=1.0E-12 RS=1MEG
+ GAIN=3000 FNDP=150MEG VSAT=2.5 CMRR=-100DB
.MODEL SWI NSW VH=0.5 VTH=0.4732 GOFF=0.01U RON=1.5K
.SUBCKT OPAMP O1 O2 I1 I2
VINOI E1 I1 NOISE 7.86E-18 4.28E-14 1.33
OPAX E1 I2 O1 O2 AMP
.ENDS
.SUBCKT IT PHI INP OUT
SO PHI INP OUT SWI
.ENDS IT

```

Transient Noise Analysis
Example 2-Switched Capacitor Filter
```

*** INTEGRATOR 1
XS1 C 9 0 IT
XS2 CB 9 8 IT
XS3 CB 10 0 IT
XS4 C 10 7 IT
XS5 C 11 0 IT
XS6 CB 11 1 IT
XS7 C 12 0 IT
XS8 CB 12 4 IT
XS9 C 13 0 IT
XS10 CB 13 2 IT
*** INTEGRATOR 2
XS11 CB 15 0 IT
XS12 C 15 14 IT
XS13 CB 16 5 IT
XS14 C 16 0 IT
*** INTEGRATOR 3
XS15 C 18 0 IT
XS16 CB 18 17 IT
*** INTEGRATOR 4
XS17 CB 20 0 IT
XS18 C 20 19 IT
XS19 CB 21 3 IT
XS20 C 21 0 IT
*** INTEGRATOR 5
XS21 C 23 0 IT
XS22 CB 23 22 IT
XS23 C 24 0 IT
XS24 CB 24 6 IT
*** INTEGRATOR 6
XS25 CB 26 0 IT
XS26 C 26 25 IT
*** OUTPUT NODE 5
X1 1 0 0 8 OPAMP
X2 2 0 0 14 OPAMP
X3 3 0 0 17 OPAMP
X4 4 0 0 19 OPAMP
X5 5 0 0 22 OPAMP
X6 6 0 0 25 OPAMP
X7 OUT 0 5 OUT OPAMP

```
```

C20675 10 9 9.23530E-01PF
C20678 9 11 4.52374E-01PF
C20680 12 9 8.43906E-01PF
C20683 13 9 6.42120E00PF
C20698 8 1 9.10828E00PF
C20719 8 5 2.66016E-01PF
C20720 12 18 7.09376E-01PF
C20722 17 3 1.26865E00PF
C20725 12 23 1.64195E00PF
C20729 23 16 1.23994E00PF
C20732 24 23 6.27077E00PF
C20747 22 5 8.70857E00P
C20767 22 1 7.09376E-01PF
C21108 11 15 9.29551E00PF
C21124 16 15 2.66016E-01PF
C21125 2 14 1.70001E01PF
C21153 11 20 9.73922E-01PF
C21155 16 20 7.09376E-01PF
C21157 20 21 6.92543E00PF
C21169 4 19 1.02160E01PF
C21186 16 26 3.50407E00PF
C21192 11 26 2.66016E-01PF
C211936 25 6.22576E00PF
*** INPUT SIGNAL AND CLOCK ***
VIN 7 0 pwl (0 0 200n 1 11u 1 11.2u 0)
VCLK00 C O PWL (0 -5 200n +5 10000n +5 10200n -5 20000n -5 R)
VCLKB00 CB 0

+ PWL (0 +5 200n -5 10000n -5 10200n +5 20000n +5 R)
.TRAN 1M 4M
.NOISETRAN FMIN=1 FMAX=50K NBRUN=20
.OPTION FREQSMP=150K BE
.PLOT TRAN V(5)
.END

```

\section*{Chapter 13 Working with S, Y, Z Parameters}

\section*{Introduction}

A set of commands in Eldo allows you to extract the large signal S parameters (Scattering parameters), the Y parameters (Admittance) or the Z parameters (Impedance) in the frequency domain for a specified circuit. The circuit can have any number of ports.

Eldo enables the simulation of circuits including any number of N-port blocks described by a frequency tabulation of their S (Scattering), Y (Admittance) or Z (Impedance) parameters. It does so by reading the \(\mathrm{S}, \mathrm{Y}, \mathrm{Z}\) parameter data from a Touchstone \({ }^{\circledR}\) format file.

\section*{Simulation Setup for S, Y, Z Parameter Extraction}

Special sources must be added at each port of the circuit to be analyzed. The number of the port and the reference impedance for \(S\) parameters must be specified in the Eldo control file as follows:

\section*{Source Syntax}
```

VYY NP NN IPORT=VAL [RPORT=VAL] [CPORT=VAL] [LPORT=VAL] [MODE=KEYWORD]
VYY NP NN IPORT=VAL ZPORT_FILE=string [CPORT=VAL] [IPORT=VAL]

+ [MODE=KEYWORD]
IYY NP NN IPORT=VAL [RPORT=VAL] [CPORT=VAL] [IPORT=VAL] [MODE=KEYWORD]
IYY NP NN IPORT=VAL ZPORT_FILE=string [CPORT=VAL] [IPORT=VAL]
+ [MODE=KEYWORD]

```

\section*{Parameters}
- yy

Name of the port.
- NP

Name of the positive node.
- NN

Name of the negative node.
- IPORT

This is a strictly positive number that is unique and is used as the port number: this number is used for naming the outputs (for instance, . PLOT AC \(S(1,2)\) ). An error message will be
issued if two port instances have the same value for IPORT, or if an IPORT is missing (for example maximum IPORT number found in the netlist is 4 , and there is no instance with IPORT 3).
- RPORT

Value of the Reference Impedance in Ohms. Default value is \(50 \Omega\).
- CPORT

Capacitor placed in series (for V source) or parallel (for I source) with rport. Defaults to 0, in which case it behaves like a zero voltage source (i.e. CPORT would have no effect).
- LPORT

Inductor placed in series (for V source) or parallel (for I source) with rport. Defaults to 0 .
- ZPORT_FILE

Specifies the Touchstone file name that contains the port source with a complex impedance. Large signal \(S\) parameters can be extracted from a complex port impedance.
- MODE=SINGLE \(\mid\) COMMON \(\mid\) DIFFERENTIAL

Mixed-mode \(S\) parameter selection.
SINGLE specifies the port as single ended, it is dedicated to \(S\) parameter extraction. Default.
common and differential specify that the port is not single ended. Such ports are split into two linked sources that are either common (same amplitude and same phase) or differential (same amplitude but opposite phases). During S parameter extraction a "nonsingle ended" port is equally common and differential depending on which display is required. During simulation (DC, AC or TRAN) this port is either common or differential depending on the specified mode keyword.

\section*{Note}

Port numbers in \(\mathrm{v}_{\mathrm{yy}}\) instances should range from 1 to the total number of ports without discontinuity. The simulation parameters FMIN, FMAX, and Number of frequency points for the analysis are specified with a .AC command.

\section*{S, Y, Z Parameter Extraction}

Once the simulation has been setup (see "Simulation Setup for S, Y, Z Parameter Extraction" on page 1041), S, Y, Z parameters can be extracted during simulation by use of the .PRINT and . РLOT commands as described in the following subsections.

\section*{For S-Parameter Extraction}
\begin{tabular}{lll}
.PLOT & AC & SR(i, \(j)\) \\
.PRINT & AC & SI \((i, j)\) \\
.PRINT & AC & SM (i, \(j)\) \\
.PLOT & AC & SDB(i, \(j)\) \\
.PRINT & AC & SP(i, \(j)\)
\end{tabular}
.PRINT AC SGD(i, j)

\section*{For Mixed Mode S-Parameter Extraction}

Mixed mode \(S\) parameters can be extracted using the following syntax:
```

S[mn]TYPE(i,j)

```
type can be one of the following:
R Real part
m Magnitude
I Imaginary part
db Magnitude (dB)
p Phase
GD Group Delay
mn specifies the mode of ports i and \(j\) respectively, can be one of the following:
cc common-common
dd differential-differential
dc differential-common
cd common-differential
sc single-common
sd single-differential
cs common-single
ds different-single
ss single-single. Default.
The default mixed mode for \(S\) parameter extraction is single-single. If no mixed extension is specified on the output the default will change depending on how ports 1 and 2 are setup. The default rule is shown in Table 13-1.

Table 13-1. Default Rule
\begin{tabular}{|c|c|c|c|c|c|}
\hline Port 1 & Port 2 & Default & \multicolumn{3}{|l|}{Available quantities} \\
\hline Single & Single & SS & \(\mathbf{S}\left[s s^{\prime}(1,1)\right.\)
\(\mathbf{S}[\mathrm{ss}](1,2)\)
\(\mathbf{S}[\mathrm{ss}](2,1)\)
\(\mathbf{S}[\mathrm{ss}](2,2)\) & & \\
\hline Single & Balanced & SD & \[
\begin{array}{ll}
\hline \mathbf{S s s}(1,1) & \\
\mathbf{S s d}(1,2) & \mathbf{S s c}(1,2) \\
\mathbf{S d s}(2,1) & \mathbf{S c s}(2,1) \\
\mathbf{S d d}(2,2) & \mathbf{S d c}(2,2)
\end{array}
\] & \(\mathbf{S c d}(2,2)\) & \(\mathbf{S c c}(2,2)\) \\
\hline Balanced & Balanced & DD & \begin{tabular}{ll} 
Sdd \((1,1)\) & Sdc \((1,1)\) \\
Sdd \((1,2)\) & Sdc \((1,2)\) \\
\(\mathbf{S d d}(2,1)\) & \(\mathbf{S d c}(2,1)\) \\
\(\mathbf{S d d}(2,2)\) & \(\mathbf{S d c}(2,2)\)
\end{tabular} & \begin{tabular}{l}
\(\operatorname{Scd}(1,1)\) \\
\(\operatorname{Scd}(1,2)\) \\
\(\operatorname{Scd}(2,1)\) \\
\(\mathbf{S c d}(2,2)\)
\end{tabular} & \begin{tabular}{l}
\(\operatorname{Scc}(1,1)\) \\
\(\operatorname{Scc}(1,2)\) \\
\(\operatorname{Scc}(2,1)\) \\
\(\mathbf{S c c}(2,2)\)
\end{tabular} \\
\hline
\end{tabular}

Table 13-1. Default Rule
\begin{tabular}{|l|l|l|l|}
\hline Port 1 & Port 2 & Default & Available quantities \\
\hline Balanced & Single & DS & \begin{tabular}{l} 
Sdd (1,1) \\
\\
\end{tabular} \\
& & \(\mathbf{S d c}(1,1) \quad \mathbf{S c d}(1,1) \quad \mathbf{S c c}(1,1)\) \\
\(\mathbf{S s d}(1,2)\) & \(\mathbf{S c s}(1,2)\) \\
\(\mathbf{S s s}(2,1)\) & \(\mathbf{S s c}(2,1)\)
\end{tabular}

The default can be set using the . LIs command, with syntax:
```

.LIN mixedmode2port=dd|dc|ds|cd|cc|cs|sd|sc|ss

```

\section*{Example}
```

V1 in1 in2 iport=1 MODE=single
V2 in4 in5 iport=2 MODE=differential
.PLOT AC Sdb (1,1) Sscm(1,2) Ssdp (1,2) Sddr(2,2) Scdi (2,2)

```

\section*{For Y-Parameter Extraction}
\begin{tabular}{|c|c|c|}
\hline PLOT & AC & YR \\
\hline PRINT & AC & YI (i, \\
\hline PRINT & AC & YM(i, j) \\
\hline PLOT & AC & YDB (i, \\
\hline PRINT & AC & YP (i, \\
\hline RII & AC & YG \\
\hline
\end{tabular}

For Z-Parameter Extraction
\begin{tabular}{lll}
.PLOT & AC & ZR(i, \(j)\) \\
.PRINT & AC & \(\mathbf{Z I}(i, j)\) \\
.PLOT & AC & ZM(i, \(j)\) \\
.PLOT & AC & \(\mathbf{Z D B}(i, j)\) \\
.PRINT & AC & ZP(i, \(j)\) \\
.PRINT & AC & ZGD \((i, j)\)
\end{tabular}

Where \(\mathbf{S x x}_{\mathrm{x}}(\mathrm{i}, \mathrm{j}),\left(\mathrm{Yxx}_{\mathrm{x}}(\mathrm{i}, j), \mathrm{Zxx}_{\mathrm{x}}(\mathrm{i}, \mathrm{j})\right)\) give the influence of port j on port i .

\section*{Matrix Parameter Extraction}

Once the simulation has been setup (see "Simulation Setup for S, Y, Z Parameter Extraction" on page 1041) then G, H, T, A parameters can be extracted during an AC or FSST simulation by use of the .PRINT and . PLOT commands as described in the following subsections.

\section*{For G-Parameter Extraction}
\begin{tabular}{lll}
.PLOT & AC & GR(i, \(j)\) \\
.PRINT & AC & GI (i, \(j)\) \\
.PRINT & AC & GM(i, \(j)\)
\end{tabular}
```

.PLOT AC GDB(i ,j)
.PRINT AC GP(i, j)
.PRINT AC GGD(i, j)

```

\section*{For H-Parameter Extraction}
\begin{tabular}{lll}
.PLOT & AC & HR \((i, j)\) \\
. PRINT & AC & HI \((i, j)\) \\
. PRINT & AC & HM \((i, j)\) \\
.PLOT & AC & HDB \((i, j)\) \\
. PRINT & AC & HP \((i, j)\) \\
. PRINT & AC & HGD \((i, j)\)
\end{tabular}

\section*{For T-Parameter Extraction}
\begin{tabular}{lll}
.PLOT & AC & TR(i, \(j)\) \\
.PRINT & AC & TI \((i, j)\) \\
. PRINT & AC & TM (i, \(j)\) \\
.PLOT & AC & TDB \((i, j)\) \\
.PRINT & AC & TP \((i, j)\) \\
.PRINT & AC & TGD \((i, j)\)
\end{tabular}

For A-Parameter Extraction
```

.PLOT AC AR(i, j)
.PRINT AC AI(i, j)
.PRINT AC AM(i, j)
.PLOT AC ADB(i ,j)
.PRINT AC AP(i, j)
.PRINT AC AGD(i, j)

```

Where \(\mathbf{S x x}_{\mathrm{x}}(\mathrm{i}, \mathrm{j}),\left(\mathrm{Yxx}_{\mathrm{x}}(\mathrm{i}, \mathrm{j}), \mathbf{z x x}(\mathrm{i}, j)\right)\) give the influence of Port j on Port i .

\section*{Output File Specification}
.ffile \(\mathbf{S}|\mathbf{Y}| \mathbf{Z}|\mathbf{G}| \mathbf{H}|\mathbf{T}| \mathbf{A}\) [SINGLELINE] FILENAME [HZ \(|\mathbf{K H Z}| \mathbf{M H Z} \mid \mathbf{G H Z}\) ] [RI \(|\mathbf{M A}| \mathrm{DB}]\)

\section*{Parameters}
\(\mathbf{s} \quad\) Specifies \(S\) (Scattering) frequency parameters tabulation.
\(\mathbf{Y} \quad\) Specifies Y (Admittance) frequency parameters tabulation.
z Specifies Z (Impedance) frequency parameters tabulation.
G \(\quad\) Specifies G (Hybrid-G) matrix parameters tabulation.
н Specifies H (Hybrid-H) matrix parameters tabulation.
\(\mathbf{T} \quad\) Specifies \(T\) (transfer scattering) matrix parameters tabulation.
A \(\quad\) Specifies A (chain or ABCD ) matrix parameters tabulation.
filename \(\quad\) Name of the file where the S, Y, Z, G, H, T and A parameters will be stored.
singleline This enables you to obtain the S-parameter file in single line format as shown below:
```

Freq S11 S21 S12 S22

```
hz Specifies the units to be Hz. This is the default.
Khz Specifies the units to be kHz.
mhz \(\quad\) Specifies the units to be MHz.
GHz Specifies the units to be GHz.
RI Specifies Real Imaginary storage format.
MA Specifies Magnitude Angle storage format. This is the default.
DB MA with magnitude in dB .
Two-port noise parameters NFMIN_MAG, GAMMA_OPT_MAG, PHI_OPT and RNEQ are automatically written to the specified output file when a .NOISE command is specified in the netlist and the circuit to be analyzed is a two-port circuit.

\section*{Examples}
```

r1 1 2 100k
c1 2 0 10pf
V1 1 0 iport=1 rport=100
v2 2 0 iport=2 rport=20
.ac dec 10 1 100meg
-plot ac sdb (2,1)
.Ffile S sbl.par khz ri

```

In this example, the \(S\) parameters of an \(R C\) circuit are extracted between 1 Hz and 100 MHz with 10 points per decade. The reference impedance is 100 for port1 and 20 for port2. The magnitude of s21 is plotted in dB , and the extracted S parameters are stored in the file sb1.par with the frequency in kHz . The data is stored in the form of the Real and Imaginary parts.
```

V1 1 0 iport=1 rport=50
R1 1 n1 1k
C1 n1 0 100p
R2 n1 2 1k
Rc1 n1 0 100k
V2 2 0 iport=2 rport=50
.ac lin 21 1meg 21meg
.noise v(n1) V1 3
.plot noise rneq gopt bopt nfmin_mag
.ffile Z Z.par kHz ma

```

In this example the Z parameters are being extracted between 1 MHz and 21 MHz with 21 analysis points. The extracted Z parameters are stored in the file Z.par with the frequency in kHz . The data is stored in the form of the Magnitude Angle. As the circuit is a two-port circuit and there is a .nOISE command specified in the netlist then the two-port noise parameters are also stored in the output file. The output file is shown below:
```

! Data from test

# KHZ Z DB R 5.000000E+01

!
1.0000000000000000E+03 6.5542511585029786E+01 -5.7202544106307606E+01
6.4035302689753806E+01 -8.9088186330215692E+01 6.4035302689753806E+01
-8.9088186330215706E+01 6.5542511585029786E+01 -5.7202544106307606E+01
2.1000000000000000E+04 6.0025369785355387E+01 -4.3338006361865595E+00
3.7592014242230192E+01 -8.9956576643609139E+01 3.7592014242230199E+01
-8.9956576643609139E+01 6.0025369785355402E+01 -4.3338006361865711E+00
! Noise Data: Nfmin(dB) GammaOpt PhiOpt Rneq/R0
1.0000000000000000E+03 5.2661113010469025E+00 9.6890047604421903E-01
1.7851510536508835E+02 4.8497683522933400E+01
2.1000000000000000E+04 2.8441528902447214E+01 9.0554147314402922E-01
1.7956971588917614E+02 3.5225984336136335E+03

```

In the following example the \(S\) parameters of the block TWO_PORT_SUBCKT are being extracted between 10 kHz and 10 MHz with 10 analysis points per decade. The Touchstone file Z1.par defines the complex impedance of the source at port 1. The extracted S parameters are stored in the file subckt.par with the frequency in kHz . The data is stored in the form of the Magnitude Angle.
```

Vin 1 0 iport=1 zport_file="Z1.par"
Xsub1 1 0 2 0 TWO_PORT_SUBCKT
Vout 3 0 iport=2 rport=50
.ac dec 10 10000 10meg
.plot sdb(1,2) sdb (1,1) sdb (2,2) sdb (2,1)
.ffile S subckt.par KHZ MA

```

\section*{Transient Simulation of Circuits Characterized in the Frequency Domain}

\section*{Introduction}

Traditionally, high frequency circuits are characterized and simulated in the frequency domain. This is because of the difficulty of handling extremely short rise times of the order of picoseconds and the simplicity of frequency measurement.

Today with the technological advent in high frequency circuits, there is a vital need to simulate circuits in the time domain using electrical simulators. This is needed to simulate, for example,
a linear (lossy and maybe coupled) interconnection having a non-linear termination. Such problems may be solved in the frequency domain using harmonic balance. If we are interested in using pulse stimuli, the circuit must be analyzed in the time domain. Another example is the microwave simulation of passive elements, either discrete or integrated. A user defined passive element may be simulated by extracting its scattering (S) parameters using a standard ElectroMagnetic (EM) solver and then using this file as an input to an S-Model. This procedure enables the user to simulate this passive element in Eldo either with or without other linear or non-linear elements.

The main object of the S-Model GenLib library is to allow the transient analysis of precharacterized (in the frequency domain) linear high frequency circuits with any other non-linear components. The circuit is usually characterized by its scattering parameters. S-Model also allows the simulation of circuits characterized using their admittance \((\mathrm{Y})\) or impedance \((\mathrm{Z})\) parameters. The pre-characterized circuit may have any number of ports. The following paragraph gives a brief technical presentation of matrix representation of linear circuits.

\section*{Technical Background}

A two port network is completely presented by its \(\mathrm{Z}, \mathrm{Y}, \mathrm{h}\) or S matrix. As an example, consider the impedance Z matrix:
\[
\left[\begin{array}{l}
V_{1} \\
V_{2}
\end{array}\right]=\left[\begin{array}{ll}
Z_{11} & Z_{12} \\
Z_{21} & Z_{22}
\end{array}\right]\left[\begin{array}{l}
I_{1} \\
I_{2}
\end{array}\right]
\]

It is clear that this matrix relates the currents and voltages at the terminals of a given block:


An equivalent presentation is:
\[
\left[\begin{array}{l}
b_{1} \\
b_{2}
\end{array}\right]=\left[\begin{array}{ll}
s_{11} & s_{12} \\
S_{21} & s_{22}
\end{array}\right]\left[\begin{array}{l}
a_{1} \\
a_{2}
\end{array}\right]
\]

In this case, we use the \(S\) matrix or scattering parameters. \(\boldsymbol{a}_{1}\) and \(\boldsymbol{b}_{1}\) present the normalized incident and reflected waves at port 1. \(\boldsymbol{a}_{2}\) and \(\boldsymbol{b}_{2}\) present the corresponding waves at port 2. There are direct relationships between \(\boldsymbol{a}_{1}, \boldsymbol{b}_{1}, \boldsymbol{a}_{2}, \boldsymbol{b}_{2}\) and the corresponding \(\boldsymbol{I}_{1}, \boldsymbol{V}_{1}, \boldsymbol{I}_{2}, \boldsymbol{V}_{2}\).

In the case of a two port network, the I and V as a function of a and b is given by the following:
\[
\begin{aligned}
V_{1} & =\left(a_{1}+b_{1}\right) \sqrt{R_{1}} \\
I_{1} & =\left(a_{1}-b_{1}\right) / \sqrt{R_{1}} \\
V_{2} & =\left(a_{2}+b_{2}\right) \sqrt{R_{2}} \\
I_{2} & =\left(a_{2}-b_{2}\right) / \sqrt{R_{2}}
\end{aligned}
\]

For the same case, a and b as a function of I and V is given by the following:
\[
\begin{aligned}
& a_{1}=\frac{V_{1}+R_{1} I_{1}}{2 \sqrt{R_{1}}} \\
& b_{1}=\frac{V_{1}-R_{1} I_{1}}{2 \sqrt{R_{1}}} \\
& a_{2}=\frac{V_{2}+R_{2} I_{2}}{2 \sqrt{R_{2}}} \\
& b_{2}=\frac{V_{2}-R_{2} I_{2}}{2 \sqrt{R_{2}}}
\end{aligned}
\]
where \(\boldsymbol{R}_{1}\) and \(\boldsymbol{R}_{2}\) are the reference impedances of ports 1 and 2 respectively.
The S-parameters are widely used to characterize high frequency circuits, mainly because they present no difficulty in measurements while the other parameters are difficult to measure. The scattering parameters are not unique; they are defined for a given reference impedance for each port. The reference impedance \(\boldsymbol{R}_{0}\) is usually \(50 \Omega\) for all ports to facilitate measurement (standard coaxial cable has \(50 \Omega\) characteristic impedance).

In general, an n -port circuit has an \(\mathrm{n} \times \mathrm{n}\) scattering matrix of the following form:
\[
\left[\begin{array}{c}
b_{1} \\
. . \\
. . \\
b_{n}
\end{array}\right]=\left[\begin{array}{cccc}
S_{11} & . . . & S_{1 n} \\
. & . . & . & . \\
. . & . & . & . \\
S_{n 1} & . . . & S_{n n}
\end{array}\right]\left[\begin{array}{c}
a_{1} \\
. . \\
. . \\
a_{n}
\end{array}\right]
\]

\section*{Mixed-Mode S Parameters}

Bockelman and Eidenstadt \({ }^{1}\) developed a theory for combined differential and common normalized power waves (in terms of even and odd mode). Then it is now possible to characterize multiport networks at high frequencies, especially such device which are simulated by common-mode or differential-mode source, by using the extended \(S\) parameter definition. This adaptation, called "mixed-mode S parameter", addresses differential and common-mode operation, as well as the conversion between the two modes operation.

\footnotetext{
1. David E. Bockelman William R. Eisenstadt, "Combined Differential and Common-Mode Scattering Parameters: Theory and Simulation" July 1995.
}

According with this new definition, we can see that a two port \(S\) parameters form a \(4 x 4\) matrix containing the mixed-mode S parameters (differential-mode, common mode and cross-mode \(S\) parameters). Consider the following differential circuit, each port can support the propagation of differential-mode and common-mode waves


The response of this differential circuits to a stimulus can be expressed with the mixed-mode \(S\) parameter matrix:
\[
\left[\begin{array}{l}
b_{d 1} \\
b_{d 2} \\
b_{c 1} \\
b_{c 2}
\end{array}\right]=\left[\begin{array}{llll}
S_{d d 11} & S_{d d 12} & S_{d c 11} & S_{d c 12} \\
S_{d d 21} & S_{d d 22} & S_{d c 21} & S_{d c 22} \\
S_{c d 11} & S_{c d 12} & S_{c c 11} & S_{c c 12} \\
S_{c d 21} & S_{c d 22} & S_{c c 21} & S_{c c 22}
\end{array}\right]\left[\begin{array}{l}
a_{d 1} \\
a_{d 2} \\
a_{c 1} \\
a_{c 2}
\end{array}\right]
\]
where the partition labeled \(S_{d d}\) are the differential-mode S parameters, \(S_{c c}\) are the commonmode S parameter, and \(S_{c d}\) and \(S_{d c}\) the cross-mode S parameters. The \(a_{d i}\) and \(b_{d i}\) are the normalized differential-mode stimulus and response waves; \(a_{c i}\) and \(b_{c i}\) are the normalized common mode stimulus and response waves. The definition of these normalized waves are:
\[
\begin{aligned}
& a_{d 1}=\frac{1}{\sqrt{2}}\left(a_{1}-a_{2}\right) \\
& a_{c 1}=\frac{1}{\sqrt{2}}\left(a_{1}+a_{2}\right) \\
& b_{d 1}=\frac{1}{\sqrt{2}}\left(b_{1}-b_{2}\right) \\
& b_{c 1}=\frac{1}{\sqrt{2}}\left(b_{1}+b_{2}\right) \\
& a_{d 2}=\frac{1}{\sqrt{2}}\left(a_{3}-a_{4}\right)
\end{aligned}
\]
\[
\begin{aligned}
& a_{c 2}=\frac{1}{\sqrt{2}}\left(a_{3}+a_{4}\right) \\
& b_{d 2}=\frac{1}{\sqrt{2}}\left(b_{3}-b_{4}\right) \\
& b_{c 2}=\frac{1}{\sqrt{2}}\left(b_{3}+b_{4}\right)
\end{aligned}
\]

In general, an n-port has a \(2 \mathrm{n} \times 2 \mathrm{n}\) mixed-mode S parameter matrix of the following form:
\[
\left[\begin{array}{c}
b_{d 1} \\
\ldots \\
b_{d n} \\
b_{c 1} \\
\ldots \\
b_{c n}
\end{array}\right]=\left[\begin{array}{cccccc}
S_{d d 11} & \ldots & S_{d d 1 n} & S_{d c 11} & \ldots & S_{d c 1 n} \\
\ldots & \ldots & \ldots & \ldots & \ldots & \ldots \\
S_{d d n 1} & \ldots & S_{d d n n} & S_{d c n 1} & \ldots & S_{d c n n} \\
S_{c d 11} & \ldots & S_{c d 1 n} & S_{c c 11} & \ldots & S_{c c 1 n} \\
\ldots & \ldots & \ldots & \ldots & \ldots & \ldots \\
S_{c d n 1} & \ldots & S_{d c n n} & S_{c c n 1} & \ldots & S_{c c n n}
\end{array}\right]\left[\begin{array}{c}
a_{d 1} \\
\ldots \\
a_{d n} \\
a_{c 1} \\
\ldots \\
a_{c n}
\end{array}\right]
\]

\section*{Implementation Issues}

Eldo uses three methods to simulate an S-Model given by S, Y, or Z parameters. These methods are briefly described below:
- Complex Pole Fitting (CPF) technique is a method based on complex-pole fitting of the original dependence. During an initial "fitting" stage, the model's given dependence is represented as a sum of simple first-order components, each one defined by its complex pole and residue. The result of fitting is re-usable; once generated, the list of poles and residues is stored in a *.pls file and can be used repeatedly for simulations without the need to re-fit. This file has the same name and location as the original data (Touchstone) file.

The representation of frequency dependence created by fitting allows fast and accurate transient simulation of the S-Model. Simulation progresses linearly in time, using an effective, recursive, convolution-based algorithm. Although poles/residues can be used to build an equivalent circuit, this is not needed or recommended, for performance reasons: the model-evaluation time in CPF is less by a factor of 5-7 than that for the equivalent circuit built from the same poles.

Due to the very nature of fitting, the CPF method always results in a causal solution. It also has a delay-extraction capability useful when simulating transmission lines or connectors.
- Digital Signal Processing (DSP) technique is an alternative approach that transforms the frequency-domain data into time domain parameters via inverse FFT, Hilbert transform and convolution. Important modifications were made to these basic algorithms to allow
both periodic and non-periodic dependencies, to ensure the causality of the system, to account for singularities in matrix representation and to ensure high-speed convolution.

If the circuit frequency response is naturally periodic (as for delay-containing operators) and is given only in a fraction of a single period, the DSP method is recommended to ensure accurate simulation. In this case, the last point given in the input data file should correspond to the half-period of the dependence.
- System identification (SI) technique is a third method that represents S-parameters in the form of a rational function in ' \(s\) ' (Laplace variable). These functions are then converted into systems of linear differential equations so that Eldo can solve them during the transient analysis.

With the above three methods, Eldo can efficiently solve a wide variety of problems. Frequency dependencies can be either quite smooth or with a large number of sharp resonant peaks (up to many hundred). The user may specify input data either with equidistant frequency points, starting from zero or not; or give them in any other way, (for example, logarithmically spaced) relevant to the method of data acquisition.

Of course, one can expect accurate simulations only if the original data is complete and accurate. The frequency dependence given should completely encompass the range of interest, from the lowest to the highest operation frequency. For example, high accuracy at DC is unlikely if the data starts from non-zero frequency. Similarly, accurate simulation of short transitions, lasting for hundred ps , is impossible if the highest point is far below tens of GHz . Also, the data points should be given with good resolution, sufficient to reproduce the shape of the dependencies. For example, many more points are needed to describe a dependence with many sharp peaks than for a smooth one, even if they are both defined in the same frequency range. Finally, the input data should be causal, so that the real and imaginary parts of the frequency dependence satisfy the dispersion Kronig-Kramers relation. In reality, data becomes slightly non-causal due to unavoidable measurement/simulation errors, especially (typically) at higher frequencies. However, serious measurement errors (like taking the negated phase) cause catastrophic non-causality that will lead to improper simulation results.

\section*{Applications}

S-parameters can originate from the following:
- Simulation of passive networks using an electromagnetic solver.
- Measurements from a passive network (interconnects, transmission lines, passive filters, and so on).
- Frequency-domain simulation of passive networks (AC analysis).
- Data sheets of active or passive devices.

The major applications of S-Model are as follows:
- Transient simulation of microwave linear circuits originally described by its response in frequency domain.
- Transient simulation of interconnects together with non-linear drivers/loads, either for VLSI or GaAs integrated circuits, using either their calculated or measured scattering parameters.
- Lossy transmission-line transient simulation in the presence of either linear or non-linear drivers/loads.
- Transient simulation of arbitrary (or user-defined) passive microwave circuits after extracting their S-parameters (using a standard electromagnetic solver).

\section*{Functionality}

\section*{Basic Functionality}

The S-model implemented in Eldo is a building block that makes possible DC, AC, and Transient simulation of circuits with any number of N-ports described by their S (Scattering), Y (Admittance), or Z (Impedance) parameters, in the form of tabulated data in the frequency domain.

The tabulated data is contained in an ASCII data file in the Touchstone® format. This format is briefly described in "Touchstone Data Format" on page 1058. When giving the instance of the model in the Eldo netlist file, you can specify the data file either by setting an index associated with the file's name, or by explicitly defining the name of the file. The optimal of the three algorithms discussed above, Complex Pole Fitting (CPF), Digital Signal Processing (DSP), and System Identification (SI), is selected by the internal Eldo monitor that allows great flexibility of simulation. You can also specify this method directly.

\section*{Detailed Functionality}
- Simulation of N-ports with no restriction on N. N is determined automatically by the Eldo parser according to the number of pins.
- Any number of instances of the same model, any number of different models.
- All SST and MODSST simulation types are supported.
- DC Simulation.
- AC Simulation. When the CPF algorithm is chosen either by the monitor or the user, the frequency response of the system is computed based on the found poles/residues, to enable smooth and causal simulation results. In the case of the DSP method, AC simulation is performed by interpolation and extrapolation of the tabulated parameters, with the response made symmetrical around the maximal tabulated frequency point, and the obtained spectrum is made periodic. With the SI algorithm, AC simulation produces the frequency response of the transfer function that best fits the tabulated frequency
points. If AC simulation is performed without transient simulation and without any method forced by the user, the response is obtained through interpolation of the given frequency-domain data points.
- Transient Simulation. Transient simulation is obtained through the application of the most appropriate of the CPF, DSP, or SI algorithms.
- Input data can be specified as S, Y, Z, G, H, T or A parameters.
- Tabulated data may have linear, logarithmic, or irregular distribution in its frequency range. Frequency values may start from 0 Hz or any positive value. Any number of points is allowed.
- The choice of the CPF, DSP, or SI algorithm can be forced through a parameter of the model. All algorithms allow any kind of spacing. However, since internally DSP requires linearly spaced \(\mathrm{K}^{2}+1\) data points starting at zero frequency, it uses interpolation and extrapolation of the input data to satisfy this requirement.
- Simulation is possible with the Eldo default options.
- For an N -port block ( \(\mathrm{N}>1\) ), port impedances can be identical, or different for each port.
- Speed-optimized C-FAS model.

\section*{Instantiating a Block Defined by S-Parameters}
```

.MODEL FBLOCK MACRO LANG=C
YNAME FBLOCK PARAM:

+ [M=VAL]
+ [IDX_M=VAL]
+ [NO_DELAY=VAL]
+ [GROUPFIT=VAL]
+ [SYMMETRY=VAL]
+ [FORCE_PASSIVITY=VAL]
+ [FORCE_REFIT=VAL]
+ [EXTRAP_TO_DC=VAL]
+ [POLE_REDUCTION=VAL]
+ [HIGH_PRECISION=VAL]
+ [MAXROW=VAL]
+ [MAXCOL=VAL]
+ [IDX_F=VAL]
+ STRING: FILENAME
+ PIN: IP1 IN1 ... IPN INN

```

The first line (.MODEL) is the reference to the C-FAS model, where the entity is called fblock. The other lines are the model parameters.

\section*{Note}

This .model line is optional. This declaration is not a requirement of Eldo when referencing embedded Eldo FBLOCK models.

The keyword Param: precedes the list of parameters, (each one shown in brackets as they are all optional). Most of the options, except for m, IDx_m and no_delay, are specific to the CPF method.
\(\mathbf{m}\) is a device multiplier parameter, simulating the effect of multiple S-block elements in parallel. Default value is 1 .

IDX_M is a parameter that forces a specific algorithm to be used (IDX_m=0 forces the CPF algorithm, IDx_M=1 specifies DSP, IDx_M=2 specifies SI). The default value of IDx_M is 0 (CPF).
no_delay is used to allow or prevent delay extraction in the CPF or DSP methods. no_delay \(=0\) allows delay extraction, no_delay=1 forbids it. The default value is 0 .

GROUPFIT=1 is used in CPF to force group fitting instead of individual for every matrix component. As a rule, with this option, fitting requires less effort but this might compromise accuracy. By default, its value is 0 that corresponds to individual fitting.

Symmetry=0 disables the default assumption (symmetry=1) made in CPF on the fitting stage that the original S (or Y or Z ) matrix is symmetric. Matrix symmetry is a valid assumption as long as the S-model describes a reciprocal subcircuit. We cannot simply rely on symmetry of the matrices in the input data. Very often, the input matrices generated by field-solvers or measured from reciprocal systems, are not strictly symmetric, however they should be handled as symmetric.

FORCE_PASSIVITY=val enables or disables each of the two different types of passivity enforcement available in the CPF method. These types are (1) pre-fit passivity enforcement, in which the original sampled data is worked with to make it "passive," and (2) post-fit enforcement, in which poles/residues are corrected in such a way as to make the approximation strictly passive.

FORCE_PASSIVITY=0 (default) means there is no passivity enforcement.
FORCE_PASSIVITY=1 activates pre-fit passivity enforcement.
FORCE_PASSIVITY=2 activates post-fit enforcement.
FORCE_PASSIVITY=3 activates them both.
Pre-fit passivity enforcement is recommended for all passive devices. It removes occasional passivity violations from the input data (which may result from measurement errors). However, even for the passive data created by pre-fit passivity enforcement, fitting may still result in a non-passive model if this data is defined within a limited frequency range (typical case). With two different methods of passivity enforcement, you can determine the true reason for nonpassivity: poor accuracy of the input data or fitting errors. The reason for both could be incomplete frequency range, non-causality, or insufficient resolution of the input data. For causal, accurate, and smooth input data, fitting accuracy is quite high.

If non-reciprocal linear active devices (such as amplifiers or filters) are to be simulated, both symmetry and force_passivity should be disabled.

FORCE_REFIT=1 forces fitting in CPF regardless to whether the corresponding .pls file is already present or not. This might be needed if we want to redo fitting with different options, such as force_passivity. However, you should be careful in using such an option, it should be disabled after the desired fit is built. By default, force_refit is disabled.

EXTRAP_TO_DC=1 restores a missing point at zero frequency (DC) by extrapolating the curve from low frequency points given in the Touchstone file. If the DC point is present in the input data, this option has no effect. Compared to the default case (extrap_to_dC=0) it allows, as a rule, to achieve better accuracy in DC simulation when the point at zero frequency is not given.

POLE_REDUCTION=1 (default value) enables the mode of transient simulation in which some of the fitted poles (that are too fast, too slow or too small) are removed in order to speed-up the solution. This mode typically gives up to \(30-50 \%\) reduction in solution time when the step of the transient solution is fixed. The decision about pole reduction is made from considering the solution step (pole is too "fast"), or the duration of the simulation interval (pole is too "slow"). Therefore, the set of actually used poles is defined "dynamically" from considering the parameters of the .TRAN command. The generated list of poles/residues ( \({ }^{*} . p l s\) ) file remains unaffected. Pole reduction does not considerably affect the solution accuracy. However, if the precise simulation is needed, the option can be disabled by setting pole_reduction=0.

HIGH_PRECISION=1 increases fitting accuracy by allowing more poles than in regular mode (with default value 0 ). This option can be useful for verification purposes, for example if a "reference solution" is required. However, it is not recommended if the input data itself is not very accurate. Also, since high-precision fitting produces more poles, it makes simulation slower.

MAXROW=VAL sets the limit (val/2) to the frequency points of the original dependence used in fitting. By default, MAXROW=40000, that corresponds to 20,000 points.

MAXCOL=VAL sets the limit (val/2) to the maximal order of complexity for fitting in CPF. By default, MAXCOL=1500, that corresponds to a order of complexity of 750 . For very complicated (sharp, irregular) dependencies it is sometimes reasonable to reduce the order of complexity, especially if we have reasons not to entirely trust the input data at higher frequencies. As a rule, reducing order of complexity is a better strategy than reducing the number of points to consider (MAXROW).

The keyword string: is to define the name of the touchstone file, containing the input data. Path definition is allowed. Another way of defining the data file is using the parameter IDx_f. Note that the parameter IDx_f should be defined under the keyword PARAM: together with all other parameters, not under the STRING: keyword. This parameter defines the index (integer number) VAL associated with the \(S\) parameter file (IDx_F=VAL implies that the input parameter file is named sbVAL.par).

The \(2 \times \mathrm{N}\) pins of the N -port model will be connected to nodes IP1 IN1 ... IPN INN.
A single reference node is supported. When the number of pins of the fblock model is even, Eldo considers that each port has two pins. When the number of pins is odd, Eldo considers the reference pin is the same for all ports (and it is the last pin).

Any model may be instantiated as many times as required with the same or different input data file.

Any fblock instance will contribute to the global noise results of .noise and . sstnoise. If the Touchstone format file contains noise parameters then they will be used to compute the noise contribution, otherwise the simulator will use the Twiss formula.

\section*{Twiss Formula}
\[
C_{y}=2 k t\left(Y+Y^{H}\right)
\]

Where:
\(\mathrm{Cy}=\) Noise Correlation Matrix
\(\mathrm{k}=\) Boltzmann Constant
\(t=\) Temperature
\(Y=Y\) Parameter Matrix
\(\mathrm{H}=\) Hermitian Matrix (complex conjugate transpose)
The fblock file parameter is searched with the same methodology as searching library files, see "Search path priorities" on page 694. This means that if the FBLOCK file is not found in the current directory, the library where the corresponding FBLOCK instance was found is searched first if FBLOCK was actually read from a library. If not found, the directories are searched in the order specified by the option search.

\section*{Examples}
```

.model dio D rs=4.68 bv=6.1 cjo=246p
.model Fblock macro lang=c
vin 1 0 dc 5 ac 1 pulse(0 5 1n 1n 1n 5n 10n)
rin 1 2 50
ytline Fblock param:

+ force_passivity=1
+ string: C:\s-parameterdata\lowpassfilter.s2p
+ pin: 2 0 3 0
dout 3 0 dio
.ac dec 10 1 10meg
.tran 10n 100n
.plot ac vdb(2) vdb(3)

```
```

.plot tran v(1) v(2) v(3)
.end

```

In the above example, we define a block ytline. By default, the CPF method runs. Delay extraction is allowed (if feasible), fit is set to individual, the model is assumed symmetric, passivity enforcement is set for pre-fit stage; refit, extrapolation to DC, and high precision flags are disabled, and the parameters maxcol, maxrow are set to their default values, 1500 and 40,000 respectively. The file name is given in conventional form, by using the keyword "string:".
```

.subckt sparam_2p p1 p2 grnd
.model Fblock macro lang=c
y2port FBLOCK param:

+ idx_f=4
+ idx_m=1
+ no_delay=1
+ pin: p1 grnd p2 grnd
.ends sparam_2p

```

In this example, a block y2port refers to an S-parameter file sb4.par (since idx_f=4). Here, the S -block is described as a subcircuit. The DSP method is chosen and delay extraction is prevented.

\section*{Touchstone Data Format}

The Touchstone \({ }^{\circledR}\) data format file is an ASCII text file in which data appears line by line: N lines for each data point of N ports. The data points are stored in increasing order of frequency.

The first of these \(N\) lines consist of a frequency value and \(N\) pairs of values for \(S, Y, Z, G, H, T\) or A parameters.

The ( \(\mathrm{N}-1\) ) following lines contain N pairs of values.
Values are separated by one or more spaces or tabulations.

1
Tip: Touchstone data format files follow general syntax rules. The standard is available from the EDA Industry Working Groups website:
http://www.eda.org/pub/ibis/connector/touchstone_spec11.pdf

Example of S parameters for three ports:
F \begin{tabular}{rllllll} 
SR11 & SI11 & SR12 & SI12 & SR13 & SI13 \\
SR21 & SI21 & SR22 & SI22 & SR23 & SI23 \\
SR31 & SI31 & SR32 & SI32 & SR33 & SI33
\end{tabular}

\section*{Note}

Two ports may also represented in single line format but will have a different parameter order (notice that s12 and s21 are swapped), see below.
Two ports on a single line:
Freq S11 \(\quad\) S21 \(\quad\) S12 \(\quad\) s22
Two ports on dual lines:
Freq S11 S12
S21 S22

Comment lines begin with an exclamation mark (!). The first un-commented line in the file must be a specification line. An optional specification line begins with the number symbol (\#) followed by a space. Then, several optional parameters are specified in the following order:
- Frequency Unit ( \(\mathrm{Hz}, \mathrm{kHz}, \mathrm{MHz}, \mathrm{GHz}\) ). Default value is Hz .
- Parameter type (S, Y, Z, G, H, T, A). Default value is S.
- Data format (MA, DB, RI). Default value is RI. MA means Magnitude in Volts, and the phase in degrees. DB means Magnitude in dB, and phase in degrees. RI means Real and Imaginary parts.
- Reference impedance of each port (when all the ports have the same reference impedance, only one may be specified). Default value is all ports with the same \(50 \Omega\) reference impedance.
\# [ \(\mathrm{Hz}|\mathrm{kHz}| \mathrm{MHz} \mid \mathrm{GHz}] \quad[\mathrm{S}|\mathrm{Y}| \mathrm{Z}|\mathrm{G}| \mathrm{H}|\mathrm{T}| \mathrm{A}] \quad[\mathrm{RI}|\mathrm{MA}| \mathrm{DB}]\)
+ [R Val|R1 Val1 ... Rn Valn]
- The two-port noise parameters (NFMIN, GAMMA_OPT_MAG, PHI_OPT, RNEQ) can be used when you have specified a . NoISE command in the netlist and when the circuit to be analyzed is a two-port circuit. NFMIN is the minimal noise figure of the two-port. GAMA_OPT is the magnitude of the optimal reflection coefficient associated with the minimum noise figure. PHI_OPT is the angle of the optimal reflection coefficient associated with the minimum noise figure. RNEQ is the equivalent noise resistance.

\section*{Example}
\# khz \(\mathbf{s}\) ri \(\quad\) r 50
Frequency values are in kHz , the data are S-parameter data, they are stored in the format Real and Imaginary part and the reference impedance is \(50 \Omega\) for each Port.

\section*{Mixed Mode S-Parameter Extraction}

When extracting mixed mode \(S\) parameters the contents of the Touchstone output data file will change. For example the file header for a 2-port network may appear as follows:
! Data from foo

Working with S, Y, Z Parameters Touchstone Data Format
```

! S11 = SDD11
! S12 = SDS12
! S13 = SDC11

# HZ S RI R1 1.000000E+01 R2 1.000000E+00

```

\title{
Chapter 14 Speed and Accuracy
}

\section*{Introduction}

This chapter describes the algorithms in Eldo and their control options. Most of the information relates to the transient analysis, as it is the most time-consuming analysis, and also the most frequently used analysis.

The most relevant trade-off that users are interested in is the speed/accuracy trade-off. Circuitlevel transient simulation is indeed the numerical resolution of an algebraic differential system of equations. As such, it is not an exact procedure (unlike the linear AC or NOISE analyses), and many 'switches' can be used to control the accuracy of the results. Usually, improved accuracy comes with an increased CPU time.

Eldo includes three different algorithms, namely NR (Newton-Raphson), OSR (One Step Relaxation) and IEM (Integral Equation Method). Each of these algorithms has its own set of properties.
- NR is the most general and robust algorithm, and it is always used by default. It is very accurate, and applicable to all kind of circuits, without restriction. NR is used by the vast majority of 'SPICE' commercial simulators, because of its generality.
- OSR is efficient for the analysis of large, loosely-coupled circuits, typically digital CMOS. It is reasonably accurate, and the CPU time grows almost linearly with the size of circuit, whereas the CPU time growth rate of NR is super-linear. However OSR works really well only if the loose-coupling assumption is verified, thus it is much less general than NR. For example OSR is not effective with bipolar circuits. Further details on OSR can be found in "OSR Algorithm" on page 1073.
- IEM is yet another completely different algorithm, unique to Eldo. It is useful when very high accuracy is desired and/or when NR shows stability issues. Some components cannot be formulated in a way that is compatible with IEM, thus it is also less general than NR. Further details on the use of IEM can be found in "IEM Algorithm" on page 1072 and "Integral Equation Method (IEM)" on page 1099.

Unless explicitly triggered, by the user with commands and/or switches in the netlist, neither OSR nor IEM are used by Eldo. By default, only NR is used, for the whole circuit.

Eldo is also able to partition a circuit into different parts that are simulated with different algorithms. For example, some partitions can be simulated with classical NR, whereas others are simulated with OSR or IEM. Each partition can use its own accuracy control parameters.

\section*{Speed and Accuracy in Eldo}

Eldo has numerous control parameters to choose the most appropriate speed/accuracy compromise. This chapter attempts to present these parameters, covering the most important ones, and some of the less important ones.

The system of equations that represent the behavior of a circuit cannot be solved analytically, apart from trivial cases. Thus a simulator has to use numerical algorithms to find an approximate solution.

In the case of transient analysis, the problem to solve is to find the solution of a DAE (Differential Algebraic Equations) system. To simplify, and deliberately using loose notations, the 'solution' that the simulator tries to find is a set of \(N\) voltage waveforms \(v_{n}(t)\), where \(n\) ranges from 1 to \(\mathrm{N}, \mathrm{N}\) being the number of nodes in the circuit, and t represents the time variable. These voltages are the solution of \(f\left(v(t), q^{\prime}(v(t)), t\right)=0\), where \(f()\) and \(q()\) are non-linear functions. Equation \(f()=0\) is nothing but the expression of the Kirchoff law, i.e. the sum of all currents entering a node is null, at any time. Function \(q()\) models the dynamic part of the circuit, i.e. the generally bias-dependent charges in the circuit.

This system is differential and non-linear. To solve it numerically, time is discretized, and the equations are solved at discrete time points. The time-derivatives are approximated using a socalled integration scheme or method, using current and previous values of the solution \(\mathrm{v}\left(\mathrm{t}_{\mathrm{i}}\right)\), \(\mathrm{v}\left(\mathrm{t}_{\mathrm{i}-1}\right), \ldots, \mathrm{v}\left(\mathrm{t}_{\mathrm{i}-\mathrm{m}}\right)\). The number m of previous time points used to approximate the timederivatives depends on the 'order' of the integration method. In all cases, an approximation error is introduced in this process.

Once the time-derivatives have been eliminated, the system to solve is 'simply' non-linear. Many numerical methods exist to solve this numerically. They are usually requiring a certain number of iterations, starting from an initial guess \(\mathrm{v}_{0}\), and each iteration providing, hopefully, a better estimate \(\mathrm{v}_{\mathrm{j}}\) of the solution \(\mathrm{v}_{\text {exact }}\). This iterative process will normally converge. Some criterion are needed to decide when to stop the iterative process and accept the last estimate as the 'solution' at the current time point. Again an approximation error is introduced here. One of the commonly used methods to solve non-linear systems of equations is the so-called NewtonRaphson method. It is commonly used mainly because of its generality and also for its relative robustness.

As a summary, mainly two types of errors are involved in the resolution of the system:
- Errors due to the numerical integration process
- Errors due to the numerical resolution of non-linear equations

\section*{Integration Methods}

As explained before, the process of 'eliminating' the time-derivatives in the original circuit equations is a source of error. These time-derivatives are replaced with finite differences, which
only approximate the true time-derivatives. One of the most basic approximation scheme is the Backward-Euler method, which approximates \(v^{\prime}\left(\mathrm{t}_{\mathrm{i}}\right)\) using the finite difference \(\left(\mathrm{v}\left(\mathrm{t}_{\mathrm{i}}\right)-\mathrm{v}\left(\mathrm{t}_{\mathrm{i}-1}\right)\right)\) / \(\left(\mathrm{t}_{\mathrm{i}}-\mathrm{t}_{\mathrm{i}-1}\right)\). Intuitively, it is easy to understand that the smaller the time step \(\mathrm{h}=\mathrm{t}_{\mathrm{i}}-\mathrm{t}_{\mathrm{i}-1}\), the smaller the error. More sophisticated schemes exist, which provide less error with the same time step. For example the so-called trapezoidal and Gear methods are such methods.

The numerical resolution of differential equations is a vast subject, and there exists abundant literature about the subject. Dozens of methods have been proposed and studied in depth, some of them having very attractive properties, particularly allowing to use very large time steps without running into stability issues. However, in the context of circuit simulation, many of these methods are not practically applicable. The differential equations that model an electrical network (either IC or PCB) dynamics have unfortunately 'bad', undesirable characteristics. For example, they are implicit (in most if not all formulations used in commercial simulators) and very often 'stiff' (which means that the individual time constants involved in the system can routinely exhibit orders of magnitude differences). The cost of evaluation of the non-linear functions is also very high. This unfortunate situation leaves very few good practical candidates as integration methods.

Eldo implements three methods, namely the simple Backward-Euler (BE) method, the trapezoidal method (TRAP) and the Gear method (GEAR). The trapezoidal method is the default in Eldo. It provides a very good speed/accuracy compromise. TRAP and GEAR are both second-order method, whereas BE is a first-order method. The accuracy of BE is theoretically one order of magnitude worse than TRAP or GEAR, so it is usually reserved for cases where speed is the most important criterion, and accuracy can be somewhat sacrificed. In many cases, the speedup obtained with BE is not 'spectacular', although the loss in accuracy can be significant. This is because the GEAR and TRAP methods are still relatively simple methods (the derivative approximations are not too complicated). Thus the accuracy improvement with TRAP or GEAR over BE is generally worth the extra cost of CPU time.

Although TRAP and GEAR have similar theoretical accuracy, they still have their own characteristics. TRAP has the very undesirable tendency to generate numerical 'ringing', particularly on the current variables. Ringing shows up as obviously non-physical oscillations of small (or large!) amplitude riding on top of a correct and accurate average value. The oscillations have the rhythm of the time steps, they don't belong to the circuit intrinsic time constant(s). They usually dampen over time, if the simulator properly controls the time step. This does not happen systematically with all test cases, but it is a well-known artifact of the TRAP method. All simulators, including Eldo, implement some code that tries to eliminate or reduce these oscillations, but sometimes, it may be very difficult to get rid of them entirely.

From the user point of view, thee are not many options. Clamping the maximum allowed time step is usually the most radical solution. However this may slowdown the whole simulation a lot. Increasing the accuracy may also help.

If these oscillations happen, and they are a problem (for example because the testbench attempts to measure currents with high accuracy), then the solution is to switch to the GEAR method. Much cleaner current waveforms will be produced by GEAR. However, everything has a price,
and the price here is that GEAR has its own undesirable property to artificially damp natural oscillations of the circuit. Thus, for the analysis of pure oscillators, or when trying to identify local or global instability problems in a design, GEAR is not recommended, because it will tend to artificially 'stabilize' any circuit. BE is even worse with that respect.

If you want to get a feeling of how these methods behaves with respect to damping of natural oscillations, try the following: create a pure parallel LC network between a node you will initialize at 1 Volt (using a .IC statement) and the ground (0). Pick L and C and the transient analysis duration T so that you can see about one hundred periods of the waveform (T=100.sqrt(L.C).2.pi). Try it with TRAP, then with GEAR, then with BE.

\section*{Time Step Control}

As explained in the background section, the resolution of the system of equations uses discrete time steps, and errors are unavoidable in all realistic cases. Time step control designates the set of methods used by the simulator to select these time steps, so that the accuracy of the solution is maintained within predefined tolerances.

\section*{Time Step Control Algorithms Overview}

To simplify, the time step can be controlled in three different ways. Eldo can use either:
- Local Truncation Error control (LTE)
- Rate-of-change control (DVDT)
- Iteration Count control (IC)

Some variants on these schemes are also available and detailed below, but these are the main three strategies.

By default, Eldo controls the local truncation error (LTE), and determines the time steps it can take based on estimations of this error. When a solution at time \(t\) has been accepted, to progress in time, Eldo will compute the value \(h\) of the largest time step it can take while still maintaining an acceptable LTE. Note that this is just a guess. The solution at time point \(t+h\) is predicted using the previous solutions at the previous time points. This serves as the initial guess. Then Eldo tries to achieve convergence at the new point \(t+h\). If convergence cannot be achieved, the time step is reduced using a smaller time step \(h^{\prime}\left(h^{\prime}<h\right)\), and a new resolution is attempted. If convergence is achieved, an estimate of the LTE is computed. If it is acceptable, the solution at time \(t+h\) is accepted, and a new cycle begins. If the error is found to be too large, then the time step is reduced in a way that should satisfy the truncation error constraint, and a new solution is computed. This process is reiterated until a time step and solution satisfying the truncation error criterion is found.

Thus when using truncation error control, there are two reasons why the time step may have to be reduced in the course of the transient simulation. Time step reduction can occur either because the Newton iterations do not converge, or because the estimated error on the time-
derivative expression is too large. These two dimensions (Newton convergence and LTE) are usually highly intricate.

To monitor this, a very useful option of Eldo is the NEWACCT option. If .option NEWACCT is set, Eldo reports interesting (and readable) statistics about the iteration counts, average number of iterations per time step, number of time step rejections, and so on. This can be used to double-check whether the simulator runs 'normally' or not. These statistics are reported at the very end of the output chi file. Eldo also reports some statistics in the original SPICE style, but the newacct reporting is much more readable and useful.

Convergence failure in the Newton iterations has several possible reasons. The initial guess may be simply too distant from the solution. This might happen if the chosen time step is 'overoptimistic' or if a sharp change in the circuit's state occurs within the time step. Note that the simulator anticipates sharp changes in the stimuli, and all 'break' points such as the edges in PWL or PULSE signals force coinciding time points. Another reason for convergence failure can be discontinuities in the model equations, or simply strong non-linearities.

Controlling the local truncation error (i.e. the error made while approximating the time derivatives with finite differences) is the most conservative and rigorous way to control the time steps. It will usually provide more reliable and accurate results. This is the method selected by Eldo by default.

The rate-of-change control method uses the rate of change of the voltages to control the time steps. The idea behind this method is to control the time steps used so that the voltages do not change 'too fast'. It is simpler than the LTE method, but also less accurate. There is no direct general relationship between the rate of change of the voltage and the actual truncation error, at least not under all conditions. The method can however provide accurate results if the rate of change is forced to remain small enough.

The iteration count method attempts to control the time step by monitoring only the rate of convergence of the Newton iterations. The idea being that if convergence is obtained rapidly, with just a few iterations, it probably means that the initial predicted guess was 'good', and conversely if many iterations are required, it probably means that the guess was incorrect. There is no attempt to estimate the truncation error. The control is entirely indirect, through the monitoring of the iteration count. This method is the least reliable of all and not necessarily any faster.

When selecting the time points, Eldo may also use internal heuristic rules, and, for example, adjust the time steps depending on the types of devices, the way they are connected, the scale of the simulation time, and so on, in order to obtain optimal results given the requested tolerances.

As a consequence there is no guarantee that from one release to another, the exact time point locations, or the time point density (local or global) will be the same. If the time points that Eldo selects naturally are not convenient for one reason or another, users must add explicit control options to alter this density. This can be through options such as: HMAX, INTERP,

OUT_STEP, OUT_RESOL, and so on. See further details in this chapter, and also the command ".PLOT" on page 791.

\section*{Time Step Control—Algorithm Selection with the LVLTIM Option}

To select one of the time step control methods which we described previously, the option lvitim is used. It can be set as an option in the netlist:
.option lvltim=0|1|2|3

\section*{Note}

If you are not comfortable with these notions, you should simply leave everything by default.
- LVLtim=0

With lvitim=0, Eldo controls the time step based on the rate of convergence of the Newton iterations. This is called "Iteration Count" (IC) control. The time step control algorithm in this case is really simple and only depends on three parameters, namely fr, itц3 and ITL4. The default values of these control parameters can be altered with .option statements. The algorithm is as follows:

If convergence is obtained in less than ITL3 iterations, then the time point is accepted, and the next time step is increased by a factor 2 at most. If convergence is obtained in less than ITL4 iterations then the time point is accepted, and the next time step is kept unchanged. If more than ITL4 iterations would be needed, the time step is reduced (multiplied by \(\mathbf{F T}\) ), a new prediction is made, and then a new attempt to reach convergence begins.

As apparent from the above, no estimation of the truncation error is calculated. This algorithm is usually faster, but it is also the less reliable.


\section*{Note}

If you decide to experiment with LVLTIM=0, it is highly recommended to start with the default values of \(\operatorname{FT}\), ITLI 3 and ITL4, and to be careful when altering these parameters.
- LVLTtM=1 DVDT=0

This triggers the rate-of-change time step control. The time step is adjusted depending on the parameters absvar and relvar and not on the local truncation error estimation. The time step is controlled so that no voltage changes by more than ABSVAR (in absolute value) nor by more than relvar (in relative change). The default value of absvar is 200 mV . The default value of relvar is 0.15 .
- LVLTIM=1 DVDT=-1

This hybrid variant actually uses the same algorithm as in the case of the default lvitim=2, except that time steps are not rejected when truncation error is too large. In other words,
truncation error estimation is used only to predict the time step that can be used, but if the iterations converge, the time step is accepted without LTE control. The simulation may be faster though less accurate.
- lvltim=2 (default)

This is the default time step control algorithm. It is by far the most reliable algorithm, and yields the highest accuracy. In this mode, Eldo estimates the local truncation error (LTE) and adjusts the time step accordingly. The LTE estimate is used for both time step prediction and rejection control.
A prediction of the largest time step is made, based on the LTE estimation of the previous time point. If convergence cannot be reached with this time step, the time step is reduced (divided by \(\mathbf{F T}\) ), a new prediction is made, and then a new attempt to reach convergence begins. If convergence is reached, the time point is not accepted right away. Instead, a new estimation of the LTE is calculated. If the LTE is within the tolerance, the time point is accepted (i.e. all state variables are updated, and Eldo proceeds with the next time point. If the estimated LTE is too large, the time step is rejected, and a smaller time step is retried.
The truncation error can only be estimated, and the estimation algorithms are different depending on the integration algorithm (BE, TRAP or GEAR). It happens that many times, the truncation error estimate provided by the estimation algorithm/formula is significantly larger than the exact error (this has been experimented with simple circuits for which the differential equations can be solved analytically, and thus the exact error can be computed). Thus, in most circuit simulators - and Eldo makes no exception - a correction factor can be used to compensate this 'over-estimation' and not force unnecessary small time steps.

The compensation of the truncation error is controlled with the trtol parameter. This parameter can range from 1 to 7 (the default value is 7). As TRTOL is made smaller, the estimated truncation error is made larger, and thus the time steps are globally reduced.
Note than in \(99 \%\) of cases there is absolutely no reason for you to play with trtol. The default value is correct for the vast majority of circuits and conditions.

In general, the acceptable LTE threshold is controlled by the global EPS parameter. More on LTE control can be found in "Control of the Local Truncation Error (LTE)" on page 1068.
- LVLTtim=3

With lvetim set to 3 , the time step is controlled in the same way as for \(\operatorname{lvltim}=2\), i.e. LTE estimates are used to predict and control the time steps. However, additional time points are calculated based on the TPRINT value in the .TRAN statement. For example if using:
```

.option lvltim=3
.tran 1n 1u

```
the time step control is based on the same LTE considerations as with lvitim=2, but additional time points are forced every 1 ns , regardless of any LTE considerations.
Obviously, if the TPRINT parameter of the .TRAN statement is very small, this will slow down the simulation significantly compared to LVLTIM=2, but will probably improve the
accuracy (there are not many examples where computing extra time points can reduce accuracy). If on the other hand, the TPRINT is anyway larger on average than what is required from an LTE point of view, this will have little impact on speed, and may be useful for post-processing or FFT purposes.

\section*{Control of the Local Truncation Error (LTE)}

When lvitim equals 2 or 3 (see previous section), LTE estimates are used to monitor the time step selection. Truncation error is the part of the solution error which originates from the approximation of the time-derivative terms (for example, in the case of a simple capacitor, the \(\mathrm{dv} / \mathrm{dt}\) term in the \(\mathrm{I}=\mathrm{C} . \mathrm{dv} / \mathrm{dt}\) equation) with finite-differences expressions. LTE can be estimated and monitored using the \(\mathrm{dv} / \mathrm{dt}\) terms or the v term itself.

When using LTE control to determine the acceptable time steps, Eldo may use the voltage quantities and/or the charge/flux quantities.

By default Eldo uses voltage quantities for LTE estimates. There are however situations where LTE on charge/flux is used:
- If .option qtrunc is specified, LTE will be computed on charges/flux, not on voltages. This corresponds to the way SPICE operates. This is sometimes more efficient and/or accurate for PCB applications, but often seems rather indirect to IC designers.
- If Eldo detects 'PCB-like' devices such as those shown in the list below, then LTE will be computed on charges/flux:
- Current sources above 1A
- Voltage sources above 500 V
- Inductors above 0.1 H
- Negative capacitors
- Magnetic core devices

If option qtrunc is set, LTE is computed using charges and flux quantities. In this case parameters (resp.) NGTOL, CHGTOL and FLUXTOL designate the absolute tolerances on (resp.) voltages, charges and fluxes, and RELTRUNC is the associated relative tolerance.

\section*{More about time step control}

Eldo can also 'clamp' the time step to both a minimum value and a maximum value. To clamp the maximum time step you want to allow, use the HMAX option. Eldo will perform all its normal time step control as explained previously, but still not take any step larger than HMAX. Use this option carefully, as setting HMAX to a smaller value than required may force long simulation times. Unless very clear suspicion exists that the result is corrupted because the selected time steps are too large, this option should not be used.

To clamp the time step to a minimum value, use the HMIN option. This is a rather dangerous option, because it basically prevents Eldo to use the time step it should use to maintain the accuracy within the specified tolerances. Unexpected results or failures are possible if using an inappropriate HMIN value. The default value for HMIN is 1ps. Unless you are desperately looking for speed improvements, it is best not change HMIN.

To control the 'acceleration' of the time step when convergence is easily obtained, use the HACC option. The overall goal of Eldo is to take the largest time step possible, while still providing results that are within the requested tolerances (typically specified with EPS, RELTOL, etc.). Every time a time point has been computed and accepted, Eldo will perform some analysis and computations to determine what the next optimal time step should be for the next time point. If convergence is easily obtained (that is, with very few iterations) and if the LTE constraints are verified with a large margin, Eldo will attempt to take a larger time step for the next time point by multiplying the current time step by a certain acceleration factor, as specified by HACC. The default value for HACC is 2, which means that Eldo will attempt to multiply the current time step by 2 at most.

Specifying a value with option HACC overrides the default value of 2 . This time step acceleration strategy is a compromise. Choosing a conservative value (1.1x for example) would provide very little speedup, but the next time point would most likely easily converge. Alternatively, choosing a large factor ( 10 x for example) when convergence is easily obtained is tempting, and would in theory provide a significant speedup. However, chances are high that the time point computed with the new (too) large time step will either not converge because of non-linearity, or will have to be rejected because the LTE constraints will be violated. In these cases, Eldo would then step back and recompute a new time point with a smaller time step (see option FT). Therefore, an aggressive value might be a worse choice than a conservative one. The default value, 2 , reflects this compromise and is a robust choice providing the best results on average. Unless you have very good reasons to do so, you are discouraged from changing the value of HACC.

\section*{Using a fixed time step}

A fixed internal time step can be specified by the STEP parameter; this may be useful when simulating certain classes of circuits (for example switched-capacitor circuits), however, care must be taken. Overall, it is not safe, and may cause excessively long simulation times.

If the requested STEP value is unreasonably small, the simulator may be fooled into believing that some nodes are not changing and will set them into "latency." A badly chosen fixed time step can thus sometimes have unwelcome results.

A step value that is too large may similarly cause problems. Consider a bipolar circuit when a large transition of an input signal occurs between two steps. This will nearly impossible to handle for the simulator.

Overall, using this option in the case of regular IC circuit analysis is highly discouraged.

\section*{Newton Iterations Accuracy Control}

The main parameters controlling the accuracy of the Newton iterations are reltol, vntol, abstol and ChGTOL

Whenever Newton iterations are used to solve the non-linear system of equations, the following convergence criterion for voltages, currents and charges are used:
- For node voltages:
\(|\mathrm{V}(\mathrm{i})-\mathrm{V}(\mathrm{i}-1)|<\) reltol \(* \mid \max (|\mathrm{V}(\mathrm{i})|,|\mathrm{V}(\mathrm{i}-1)|+\) vntol
where \(\mathrm{V}(\mathrm{i})\) is the value at current iteration i and \(\mathrm{V}(\mathrm{i}-1)\) the value of the previous iteration.
- For branch currents:
\(|\mathrm{I}(\mathrm{i})-\mathrm{I}(\mathrm{i}-1)|<\) Reltol \(* \mid \max (|\mathrm{I}(\mathrm{i})|,|\mathrm{I}(\mathrm{i}-1)|+\operatorname{AbStol}\)
where \(I(i)\) is the value at current iteration \(i\) and \(I(i-1)\) the value of the previous iteration.
- For charges:
\(|\mathrm{Q}(\mathrm{i})-\mathrm{Q}(\mathrm{i}-1)|<\) reltol \({ }^{*} \mid \max (|\mathrm{Q}(\mathrm{i})|,|\mathrm{Q}(\mathrm{i}-1)|+\) chetol
where \(\mathrm{Q}(\mathrm{i})\) is the value at current iteration i and \(\mathrm{Q}(\mathrm{i}-1)\) the value of the previous iteration.

The same RELTOL parameter controls the relative tolerance for voltages, currents and charges. However, when voltages, currents or charges become 'small' in absolute value, a relative tolerance becomes useless, thus absolute tolerances are required. Of course the typical orders of magnitude of voltages, currents and charges are quite different, thus the necessity to have specific absolute tolerances (VNTOL, ABSTOL, CHGTOL).

As a rule of thumb, if using the default settings, a simulation that goes well should use at most three or four Newton iterations per time step. This can be less if the circuit is almost linear, or if the settings such as the RELTOL value are relaxed. If many more iterations are needed, it means that either the time step control options have been relaxed a lot (and potentially the truncation error is large), or there are strongly non-linear characteristics in the circuit, which are difficult to solve. The number of Newton iteration will also increase if the RELTOL value is reduced to obtain more accuracy.

\section*{Global Tuning of the Accuracy-EPS}

A global parameter, exs, is used as a general controller to set the required accuracy of a simulation. When this parameter is changed, a collection of lower-level parameters are adjusted accordingly, affecting both the Newton convergence tolerances and the time step control tolerances.

Is is always possible to set these low-level parameters individually. However using EPS guarantees that the adjustments to the low-level parameters are consistent, which is not always easy to achieve for beginners or users not too familiar with circuit simulation tricks...

The parameter adjustments induced by EPS are shown in the table below (the global TUNING parameter which appears in the first line of the table is explained in the next section "Global Tuning of the Accuracy-TUNING" on page 1071).

Table 14-1. Global Tuning of Accuracy
\begin{tabular}{|c|c|c|c|c|c|c|c|c|c|}
\hline TUNING & & & STANDARD & & & ACCURATE & & VHIGH & \\
\hline EPS \({ }^{1}\) & 1e-1 & 1e-2 & 1e-3 & 1e-4 & 1e-5 & 1e-6 & 1e-7 & 1e-8 & 1e-9 \\
\hline reltol & 5e-2 & 5e-3 & 7.5e-4 & 5e-4 & 2.5e-4 & 1e-4 & \(5 \mathrm{e}-5\) & 1e-5 & 1e-6 \\
\hline VNTOL & 1e-6 & 1e-6 & 1e-6 & 1e-6 & 1e-6 & 1e-6 & \(1 \mathrm{e}-7\) & 1e-8 & 1e-9 \\
\hline CHGTOL & 1e-9 & 1e-9 & 1e-14 & 1e-14 & 1e-14 & 1e-15 & 1e-16 & 1e-18 & 1e-18 \\
\hline FLuxtol & 1e-11 & 1e-11 & 1e-11 & 1e-11 & 1e-11 & 1e-11 & 1e-11 & 1e-11 & 1e-11 \\
\hline Itol & 1e-6 & 1e-6 & 1e-6 & 1e-6 & 1e-6 & 1e-6 & 1e-6 & 1e-6 & 1e-6 \\
\hline ABStol & 1e-12 & 1e-12 & 1e-12 & 1e-12 & 1e-12 & 1e-12 & 1e-13 & 1e-14 & 1e-15 \\
\hline RELTRUNC \({ }^{2}\) & 5e-2 & \(5 \mathrm{e}-3\) & 7.5e-4 & 5e-4 & 2.5e-4 & 1e-4 & 5e-5 & 1e-5 & 1e-6 \\
\hline ChGTRUNC \({ }^{3}\) & 1e-9 & 1e-9 & 1e-14 & 1e-14 & 1e-14 & 1e-15 & 1e-16 & 1e-18 & 1e-18 \\
\hline
\end{tabular}
1. See .OPTION EPS for further information.
2. When set indirectly though EPS, RELTRUNC always gets the same value as RELTOL. RELTRUNC is only used if LTE is controlled on charges/flux, i.e. when .option QTRUNC is set.
3. When set indirectly though EPS, CHGTRUNC always gets the same value as CHGTOL. CHGTRUNC is only used if LTE is controlled on charges/flux, i.e. when .option QTRUNC is set.

Setting EPS automatically changes the low level parameters shown in the table above. However it is still possible to override some of them. For example, if using .option eps=1e-3 reltol=1e-8, RELTOL will be set to \(1 \mathrm{e}-8\), instead of \(1 \mathrm{e}-3\). VNTOL will be set to \(1 \mathrm{e}-6\), indirectly though EPS. This would not be too consistent probably, but it is still allowed.

It is important to notice that RELTOL, which is one of the main parameters defining the global accuracy, does NOT scale linearly with EPS.

\section*{Global Tuning of the Accuracy-TUNING}

Another global parameter, tuning, may be used as a general controller to define the accuracy of a given simulation. With TUNING, the user does not provide numerical values for the accuracy control switches. Instead, a qualitative flag is specified for the desired accuracy, and similarly to the effect of EPS, a number of adjustments are activated. Actually, 'accuracy' in this context should be understood as 'speed/accuracy compromise'.

The TUNING parameter can take four values, namely FAST, STANDARD, ACCURATE and VHIGH.

The names are self-explanatory. FAST can be used when the number one concern is to accelerate a simulation, and you are ready to sacrifice some accuracy to achieve this.

The FAST setting is equivalent to EPS \(=1 \mathrm{e}-3\), overridden with VNTOL=10e-6, ABSTOL=100e12 , RELTOL=1.25e-3 and CHGTOL=1e-12.

Thus FAST is not entirely equivalent to any given value of EPS. It is an adequate setting if you are not too worried about picoAmps and nanoVolts accuracy, and you want mostly a short runtime.

STANDARD, ACCURATE and VHIGH are completely equivalent to specific values of EPS (see Table 14-1 on page 1071 in the previous section).

STANDARD corresponds to the Eldo default settings, i.e. is equivalent to setting EPS=1e-3. If you do not set any option in the netlist file, this is what Eldo will use. Thousands of test cases covering all possible IC technologies have shown that it was the best compromise for what Eldo tries to achieve by default, i.e. reliable and accurate results in the shortest CPU time.

Finally ACCURATE and VHIGH (which stands for Very HIGH accuracy) will alter the tolerance switches to achieve higher degrees of accuracy, usually to the expense of longer simulation times of course. ACCURATE is equivalent to setting EPS \(=1 \mathrm{e}-6\), and VHIGH is equivalent to \(E P S=1 \mathrm{e}-8\).

The VHIGH setting must be used carefully, as it can lead to excessively long simulation times. It is however sometimes necessary, particularly for the cases of the startup phase of sensitive oscillators.

Using EPS settings smaller than 1e-9/1e-10 is usually un-reasonable and not recommended.
Setting the TUNING flag simply uses the .OPTION mechanism. For example:
.option TUNING=ACCURATE

\section*{IEM Algorithm}

With IEM, the differential system is first transformed into a system of integral equations, which is then transformed into an algebraic system by series expansion. The truncation error results from the finite number of terms in the series. In all cases, truncation error is also a function of the time step size. The IEM method is described in more detail in a dedicated chapter Integral Equation Method (IEM).

Once the non-linear algebraic system is obtained, it is solved by an iteration loop. IEM targets improvements of the accuracy of the solution (compared to Newton). It does not specifically
target large circuits, so it is mostly used for cell of macro-block simulations where accuracy is critical.

IEM is interesting for cases where high accuracy is required and/or when the default Newton method runs into numerical stability issues due to the integration methods (trapezoidal ringing for example). IEM however does not support all devices, macro-models, and so on, that Newton supports. Some devices cannot be efficiently formulated in a way that is compatible with the IEM algorithm. Thus the applicability of IEM is somewhat limited. It is mostly used for cell characterization applications. The Integral Equation Method (IEM) chapter describes the limitations of the IEM method.

\section*{Integration method}

When using IEM, the notion of integration method like BE, TRAP or GEAR, is irrelevant. The equations are cast to an integral form prior to the resolution. Thus there are no choices about a numerical integration method to use.

\section*{Time step control}

When using IEM, the time step control algorithm uses local truncation error (LTE) control. Only the LVLTIM=2 and LVLTIM=3 methods are selectable together with IEM. The other methods are not reliable enough when used together with IEM, and they will be refused by Eldo.

\section*{Accuracy control}

When using IEM, the same accuracy control parameters as those used for the default Newton method are available. Thus mainly the RELTOL and ABSTOL parameters will control the accuracy of the resolution

\section*{OSR Algorithm}

The One Step Relaxation (OSR) algorithm of Eldo is dedicated to the simulation of large MOS circuits showing weak local couplings (large-scale feedback loops are not a problem). It is a unique algorithm to Eldo. Its primary usage is the fast transistor-level simulation of large digital CMOS circuits, for which the weak local coupling assumption is generally valid. When the conditions for its applicability are met, its speed and accuracy are excellent. In many cases, it is just as accurate as the Newton method, but much faster, and also the growth of the CPU time with the circuit size is almost linear, which allows simulating larger networks. Although its capacity is still less than that of fast-SPICE timing simulators such as ADiT, it provides a quite interesting point in the speed/accuracy plane.

OSR is not particularly efficient with tightly coupled analog circuits. Better results will be obtained using either the default Newton-Raphson or IEM.

OSR can be activated explicitly or indirectly. The most straightforward way to activate OSR is to use ".OPTION OSR". If this option is set, Eldo will attempt to simulate the whole circuit with OSR. However, if the circuit contains elements that prevent OSR from being effective, or if its connectivity is such that OSR will fail, Eldo will revert back to the default Newton algorithm, for part or all of the circuit. A warning message is then displayed.

Actually, Eldo is able to simulate a circuit with certain parts handled by ORS, and other parts handled by Newton. More details on this possibility are given in the section 'Combined OSR/Newton simulation'

Additional information related to each of the cases above can be found in the appropriate sections of "Simulator and Control Options" on page 939.

\section*{OSR and the notion of latency}

When OSR is used, Eldo places the nodes for which the surrounding nodes do not show any voltage variation greater than EPS volts into 'latency'. Thereafter, Eldo effectively bypasses the calculation of such nodes. This allows significant CPU time savings, especially for large digital circuits where quite often only a fraction of the nodes are changing over one time step.

Due to the formulation of OSR, latency exploitation is very natural and effective. Latency is much more complicated to control in a reliable way in the context of the regular Newton method.

Even with OSR, latency and above all 'wake-up from latency' is however always tricky. When slowly varying signals are applied to a circuit with high capacitances, Eldo may not detect any voltage variation within one time step, resulting in nodes being placed in latency. Depending on the tolerances (EPS, this may cause incorrect simulation results. In case latency is potentially the source of problems, the . OPtion nolat command may be used to suppress the use of latency. If this option is set, Eldo will not use attempt to use latency, and will solve all nodes, whatever their activity.

\section*{Integration method}

When using OSR, the same integration methods as for the case of Newton (namely BE, TRAP and GEAR) can be used (using .OPTION METHOD=).

\section*{Time step control}

When using OSR, the default time step control algorithm is the same as in the case of Newton (LVLTIM=2), and thus it uses local truncation error (LTE) control. Only the LVLTIM=1, LVLTIM=2 and LVLTIM=3 methods are selectable together with OSR. The other method (LVLTIM=0 is meaningless in the context of OSR (there no Newton iterations when using OSR...).

\section*{Accuracy control}

The accuracy control when using OSR is much simpler than with Newton. The global parameter eps is used to control everything. Furthermore, the actual value of eps (in Volts) is directly used for the convergence control.

Accuracy of the relaxation loop and the inner loop is directly controlled by exs.
- Relaxation loop is stopped when:
\(\mid \mathrm{V}\) (irelax) - V(irelax-1)| < eps for all nodes
- Inner loop
\(\mid \mathrm{V}\) (iter) - V(iter-1)| < Eps/50 on the current node

\section*{Combined OSR/Newton simulation}

Eldo can 'partition' a circuit so that some blocks are simulated OSR and other blocks are simulated using the standard Newton algorithm. Typical candidate examples would include circuits with large digital CMOS blocks driving and/or driven by analog blocks such as voltage regulators, bandgap references, high-gain operational amplifiers, and so on.

In these cases, the speed and capacity of OSR is used to handle the large weakly-coupled sections of the circuits, and the accuracy and ability to handle tightly coupled devices of Newton is used for the analog blocks.

The partitioning can be left entirely to the discretion of Eldo, or the user can try to help and indicate which blocks (subcircuits) must be simulated with OSR or Newton. In this latter case, the partitioning is always 'indicative' only, and Eldo may choose to alter the boundaries of the partitions to accommodate the requirements of the OSR algorithm.

There are several ways to trigger these mixed OSR/Newton simulations:
- .OPTION BLOCKS=NEWTON

This first partitioning method is automatic, based on the degree of coupling between devices. A global option is set (. OPtion blocks=newton). Eldo will identify the blocks consisting of tightly coupled devices, and place them in partitions that will be solved using the Newton method. The loosely coupled nodes are placed in the OSR partition. The global circuit is solved using a relaxation loop. 'Simply', the relaxation loop operates with individual nodes and also group of tightly coupled nodes (the Newton partitions). Note that the identification of tightly coupled devices is not based on the netlist hierarchy (. subckt, and so on).
- Flag (analog) given on subckt definition

This partitioning methods 'tags' the subcircuit definitions. The subcircuit definitions tagged with (ANALOG) will be solved using the Newton method. This is useful when
the netlist hierarchy does reflect the nature and coupling level of the blocks. All nodes which are not inside user-defined (ANALOG) subckt, and which are connected only to MOSFET, grounded capacitances, or low-value floating capacitances (the threshold value for floating capacitance is set with . OPTION CAPANW= ), will be solved by OSR, all other nodes being solved by Newton. See the subcircuit definition syntax ".SUBCKT" on page 898 .
- .NWBLOCK [RELTOL=val] [VNTOL=val] <list_of_nodes>

This method is the most 'manual' one. Each Newton block is defined explicitly, with a list of nodes. Hierarchical names and wildcards in such names are allowed. Optionally the required Newton accuracy can be redefined for each block, using the reltol and vntol parameters. See the description of the .nwblock option in the Simulator and Control Options for additional details.

With any of the partitioning methods described above, OSR is 'implicitly activated'. OSR becomes the default method, and Eldo (or the user) defines what still has to be simulated with Newton.

Whenever OSR and Newton are activated simultaneously, the OSR and Newton rules for accuracy control apply to the OSR and Newton partitions respectively. For example the RELTOL and VNTOL parameters still define the accuracy of the nodes inside the Newton partitions, whereas EPS defines the accuracy of the OSR nodes.

\section*{Simulation of Large Circuits}

The Eldo circuit simulator is capable of handling very large circuits. To handle such circuits, containing several hundreds of thousands of components, memory usage becomes an important consideration.

For more information on memory requirements and dimensioning, please refer to the \(A M S\) Installation Guide.

For the simulation of large circuits, the following suggestions may help.
- Explore the manual...

There are indeed several dozens options and features which can significantly impact speed, and help with the simulation of large circuits. Some of them are extremely specific and relevant only in the presence of such or such element. A good place to start is the Simulator and Control Options chapter, which lists all available .OPTION, grouped by categories. Particularly the Simulation Speed, Accuracy and Efficiency Options section complements the present chapter with reference data.
- Use workstation with sufficient RAM and SWAP.

As with any software, an attempt to run a simulation with real memory far lower than that required to contain the circuit can result in a phenomena known as "thrashing."

When this occurs, CPU time is almost totally taken up in swapping data in and out of main memory, with little or no useful computation being made. Any tool that monitors process activity will report CPU usage, real memory usage and swap usage. When running large simulations, it is highly recommended to use of these tools to monitor the simulation processes.
- Use the 64 bit versions of Eldo.

If more than 2 GB of real memory is needed, consider using the 64 bit versions of Eldo. This is activated by using "eldo -64b-i circuit.cir" on the command line.
- Specify node number via maxnodes and maxtran options.

If you have an idea of the number of nodes and components (grounded capacitors not included) your circuit has, it is wise to specify these options:
```

.OPTION MAXNODES=VALUE MAXTRAN=VALUE

```

In this case, Eldo directly allocates the correct amount of memory, reducing the requirement of using the expensive C function realloc().
- Collapse the intrinsic MOS transistor nodes

When simulating large circuits containing mostly MOS transistors, the number of nodes grows very quickly with the number of MOS itself. By default, Eldo creates explicit internal nodes for the drain and source parasitic access resistors. Thus each MOS transistor with non-zero access resistors adds two internal nodes to the system. Although these nodes do not connect to anything else, and the sparse techniques used to solve the matrices greatly reduce the impact of these additional anodes upon the CPU time, they still contribute to create a much larger system. For example if 50,000 MOS are instantiated, the typical size of the circuit could be 30,000 or 50,000 'true' nodes, but grows to 130,000 or 150,000 with two internal nodes per MOS transistor. Even for Eldo, this is quite a change in problem size.

An option exists to 'collapse' these resistors into the drain current calculation, thus avoiding explicit creation of these intrinsic nodes. This option is nonwrmos. With this option, the effect of the parasitic resistors upon the drain current is still taken into account, although not as accurately as when the nodes are explicitly created.
Particularly, some of the overlap capacitances in the MOS model become connected to the external drain/source, whereas they really are connected to the internal nodes. This may change results slightly.

However, experience has shown that the accuracy degradation is barely measurable, particularly when these resistors remain 'small'. So, when having to simulate huge circuits, this is definitely something to try. It is however recommended to 'calibrate' the accuracy degradation caused by the option with a reasonably small circuit first. And then to decide whether this degradation is acceptable or not for the large circuit.

This option, as its name indicates, only affects MOS transistors. It has no effect upon the handling of the internal base, collector and emitter nodes of bipolar transistors, neither upon diodes.

When this option is active, there might be situations where DC cannot be found. If this happens, remove the option. Even when DC is found, if the netlist contains some MOS devices with forward biased bulk-source and bulk-drain junctions, Eldo will detect such situations during DC convergence, and will resimulate with the option disabled.
- Optimize the density of time points.

Is not always possible to directly alter the density of time points that the simulator must compute to maintain a given accuracy. However it is highly recommended to get familiar with some of the options which affect the number of time points. Particularly, the OUT_STEP, INTERP, FREQSMP and OUT_RESOL might have very significant impacts. Detailed discussion of these options can be found in "Limiting the Size of Transient Output Files" on page 793.
- Use the Periodic Circuit Speedup (pCs) option.

Used to increase the simulation speed for circuits with periodic or nearly periodic nature. PLLs in near-lock state belong to this category. The amount of speedup depends on the design nature. The speedup will be more significant with relatively large circuits. With circuits showing no periodicity at all, the option will not usually provide any speedup. Periodic Circuit Speedup is invoked by setting PCS=1|2 for BSIM3v3 models only ( \(\mathrm{PCS}=1 \mid 2\) represent two possible speed optimization methods, \(\mathrm{PCS}=1\) is more recommended) or PCS=3 for BSIM4 and BSIM3v3 models (with same speed optimization as PCS=1). Default is 0 . This option only supports the BSIM3v3 and BSIM4 models.

BSIM4, unlike BSIM3, has many parasitic configurations: gate resistors, body resistors network, bias dependent access resistors, and so on. These parasitic configurations are controlled by a set of instance and model parameters (Rdsmod, Rbodymod and Rgatemod). As the complexity of the parasitic configuration around the core model increases, the gain expected by the PCS decreases.

This option should not affect the accuracy of the results.
- Try suppressing DC analysis for large digital circuits.

This is achieved by setting the UIC option of the .TRAN command. Very large circuits are often digital circuits for which an accurate and time consuming DC analysis may not be necessary. The logical initialization performed by Eldo prior to any analysis should ensure that the transient analysis that follows will start with nodes correctly preset. Initial voltage conditions are specified using the .IC command.
- Decrease the accuracy for MOS digital circuits.

For MOS digital circuits, accuracy can often be decreased to 10 mV instead of the default value of 5 mV . This can save a large amount of CPU time.
- Employ the .use command.

It may be useful to split the circuit into a number of blocks, find DC solutions for each block and then find the DC solution of the circuit as a whole using the separate solutions as a starting point.

\section*{Tips for Troubleshooting and/or Improving Convergence and Performance}

\section*{Operating Point Calculation}

Before any kind of analysis is carried out by Eldo, a DC or operating point for the circuit in question is usually carried out, unless the UIC parameter is present in the .TRAN command.

DC and operating point convergence times can vary greatly, depending on the type of circuit simulated. Eldo provides a number of commands which may be used to speed up the convergence process. Each command is briefly described in the following subsections.

\section*{.IC \(\mathrm{V}<\mathrm{NN}>=\mathrm{VALUE}\)}

When used, Eldo fixes the specified node voltages for the duration of the DC analysis. If the uIC parameter is also present (in the . TRAN command), no DC analysis is performed and the voltages are initialized as defined in the . Ic command. All other voltages on nodes not initialized in the . Ic command are determined by Eldo itself. During subsequent analysis (transient), the node voltages are freed of their initial values, and may therefore assume different values.

1 See ".IC" on page 682 for further details.

\section*{.NODESET V<NN>=VALUE}

This command is used to help calculate the DC operating point by initializing selected nodes during the first DC operating point calculation. After the first calculation has been completed the node values are "released" and a second DC operating point calculation is started. This command is useful when the whereabouts of the DC operating point is known, enabling the simulator to converge directly to it and also for bistable circuits or circuits with more than one operating point.

\footnotetext{
1 See ".NODESET" on page 743 for further details.
}

\section*{.GUESS V<NN>=VALUE}

Enables the user to set the initial voltages to specific nodes for the first iteration of a DC operating point run.

\section*{.RAMP}

This command can be used when no DC operating point has been found using the above methods. Two ramping facilities are provided.

DC convergence algorithms are automatically used by Eldo when the standard DC algorithm fails to converge. The sequence of algorithms used is as follows: Newton, Gmin ramping, DC ramping, Transient ramping, PSTRAN, \(T^{\circ}\) ramping, and DPTRAN. The DPTRAN algorithm is used as a last attempt at convergence.

\section*{Note}
See ".RAMP" on page 852 , "GRAMP=VAL" on page 985, "PSTRAN" on page 1017, and
"DPTRAN" on page 1017 for further details.

\section*{.OPTION VMIN, VMAX}

By default, Eldo looks for the DC operating point within the limits of the circuit power supply. In the case of a circuit which contains elements that create energy, such as voltage or current controlled sources, it is possible that Eldo can look for solutions outside the expected bounds. If so, Eldo displays the message:
```

Searching operating point between [x1,x2]

```

The x 1 and x 2 limits can be controlled by the user in order to speed up the DC convergence process using the vmin and vmax parameters. It must be stressed, however, that unrealistic limits can also cause convergence problems.

\section*{.SAVE, .USE \& .RESTART}

A circuit may need to be simulated several times. In each case, the operating point must be determined although it may be the same for each run or may be only slightly different; in any case a large change of operating point is unlikely. To avoid the wasteful re-calculation of the operating point, a system is provided to store and reload the result of the DC analysis from the simulator; this significantly increases performance since operating point calculation time is thereby reduced.

The save, use and restart system is based on the commands:
```

.SAVE [FNAME] DC|END|TIME=VAL [REPEAT [ALT|SEQ]] [TEMP=VAL] [STEP=VAL]

+ [TYPE=NODESET|IC] [LEVEL=ALL|TOP] [CARLO=index]
.USE FNAME [NODESET|IC|GUESS|OVERWRITE_INPUT]
.RESTART FNAME [FILE=TMPFILE]

```

All commands listed above must be placed in the circuit description file.
The . SAve command, as its name implies, is used to save analysis data to a file.
The . USE command is intended to be used to load DC or operating point information for one or more parts of the circuit to be simulated; its application is thus in cases where a large or complex circuit is to be simulated and the DC or operating point data for parts of the circuit is already known. Multiple . USE commands may be used in a simulation.

The .restart command is different from the .use command in several ways. Firstly, whereas the . USE information may apply only to part of the circuit, . Restart data always applies to the whole circuit. In fact, the . Restart command first checks that the node names specified in the file used to "restart" the circuit, exactly correspond to those specified in the circuit description file where the .restart command is placed. The .restart command may be used to either load the operating (DC) point data and thereafter perform a transient simulation, or it may be used to restart a transient simulation from a specific point where the simulation had been interrupted in an earlier run. Obviously, to carry out a transient analysis from a specific point, the .TRAN command parameters need to be changed to specify the new simulation times.

\section*{Note}

You only need to change the .TRAN command if you want to change its STOP time. You don't need to change its START time.

The following sections describe the use of the above. First, here is a short synopsis.
```

.SAVE [FNAME] DC|END|TIME=VALUE [REPEAT] [TEMP=VALUE] [STEP=VALUE]
.USE [FNAME]
.RESTART [FNAME] [FILE=TMPFILE]

```
- FNAME

Filename, including extension, where the data is to be stored. If not specified, Eldo uses <cirname>.iic where <cirname> is the circuit filename.
- DC

Save the DC data.
- END

Save the complete simulation environment at the end of a transient analysis run, to allow a restart of the simulation from that point.
- TIME=VALUE

Save the simulation status after the specified simulation time has elapsed.
- repeat

Save the simulation status after each interval of simulation time has elapsed, as specified in time=value. The save file is overwritten each time a run is saved. This is similar to the . OPtIon SAvetime=Value command, except that the latter command is in CPU time as opposed to simulation time.
- TEMP=VALUE

Save the simulation status only when simulation temperature is equal to the value provided as parameter to TEMP. This is useful when sweeping through several temperatures.
- STEP=VALUE

Save the simulation status when the STEP parameter value, which is being swept as the result of a .STEP command, equals the value specified in the .SAVE command.
- FILE=TMPFILE

Binary output file. If the restarted simulation is to continue writing binary output data to a .\(w d b\) file, appending the new simulation data to the end of the previous . \(w d b\) file, then the previous file must be renamed or else it will be lost. The file parameter of the .restart command provides the new filename, tMPFile, for the old.\(w d b\) file. The system then concatenates the old.\(w d b\) file data with the new.\(w d b\) data in the original.\(w d b\) file.

\section*{.SAVE DC in Combination with RESTART}

The DC or operating point values for a circuit can be saved to a file and used later to greatly shorten this part of the analysis, when the circuit is re-simulated. This is achieved by employing the . SAVE DC and . USE nODeset commands, provided that circuit node names remain the same. The following steps are used, assuming that the circuit is stored in the circuit description file <cname>.cir.
1. Add the following line to the circuit description file:
```

.SAVE <FNAME> DC

```

If no filename <fname> is given, the default used is <cname>.iic.
2. Find the operating point of the circuit. This is stored in the file as specified in the . SAVE command.
3. Now change the circuit description file to include any other analysis required. Do not specify dc, uic or operating point calculation. Add to the circuit description file one of the lines:
```

.RESTART <FNAME> NODESET ! to use .NODESET or alternatively
.RESTART <FNAME> IC ! to use the .IC system

```

The simulator will attempt to use the operating point information stored in the <FNAME> file.

\section*{.SAVE DC in Combination with USE}

Eldo provides a system of combining the DC values of parts of a circuit to speed up the operating point calculation of the complete circuit. The DC state of the circuit sections which are available are stored in separate files. Such "circuit parts" may of course be whole subcircuits. In the general case, the DC data will be available on several files, called here <OPDATA_SS>. To "use" such for the DC calculation of a complete circuit, add the following lines to the circuit description file, and for each <OPDATA_SS> file:
```

.USE <OPDATA_SS> NODESET ! to use .NODESET or
.USE <OPDATA_SS> IC ! to use the .IC system

```

The simulator will attempt to use the operating point information stored in all the <OPDATA> files.
i To find out the differences between . NODESET and . IC strategies, refer to ".SAVE,
.USE \& .RESTART" on page 1080 . .USE \& .RESTART" on page 1080.

\section*{.SAVE END in Combination with RESTART}

It is possible to run a transient simulation and save the final state of the run. Thereafter, it is possible to restart the transient simulation from the time the last simulation was ended. To achieve this, the .SAVE command must be used in combination with the end parameter.

To restart the simulation, the circuit description file must be modified. The original . SAve command must be removed and the .TRAN command must be modified to reflect the new end time. Furthermore, a . restart command must be included in the circuit description file.
```

.RESTART <FNAME>

```

Using the above procedure, the simulation will produce a new binary output file (.wdb file) which contains data starting from the end of the last simulation. If it is desired to concatenate old and new.\(w d b\) files, then the old.\(w d b\) file should be renamed to say <tmpfile> and the above . Restart command modified as follows:
```

.RESTART <FNAME> FILE=<TMPFILE>

```

The system then concatenates the old.\(w d b\) file data with the new.\(w d b\) data.

\section*{More Sophisticated SAVE \& RESTART Procedures}

The complete . SAve syntax shown in the line below, includes provision to save the simulation state either periodically or at predefined times and/or temperature or sweep (STEP) parameter conditions:
```

.SAVE [FNAME] {DC|END|TIME=VALUE} [REPEAT] [TEMP=VALUE] [STEP=VALUE]

```

It is possible to save the result of the simulation periodically (with repeat), to save the run for a particular temperature (with теMP) or for a particular swept parameter (with STEP).

The previous section contains a description of each of the parameters of the . SAVE command.

In each case, the rule to restart the simulation from a predefined state is the same. In each case, to restart the simulation, the restart command needs to be added to the circuit description file and, of course, the save commands contained therein should be removed.

The transient simulation parameters in the .TRAN command may also need to be modified to reflect the new desired simulation time stop.

\section*{Aborting simulation and saving current state}

If a transient simulation run is interrupted by the user with a Control-C, Eldo prompts the user, inquiring if the simulation status should be saved. If the user answers in the affirmative, the simulation data is saved in a file called <cirname>.sav where <cirname> is the name of the circuit description file with no extension.

If the user wishes to restart the software from this interrupted point, then the circuit description file should be modified to include the command:
```

. RESTART

```

The simulation will then be restarted automatically from the time it was interrupted. The .TRAN command needs to be updated. Options and/or stimuli might be changed as well.

\section*{Chapter 15 \\ Eldo Reduction}

\section*{Introduction}

Eldo allows you to verify design functionality and timing including the effects of physical layout. In order to include these effects of layout, you must generate a netlist that includes parasitics extracted from layout using an extraction tool such as \(x\) Calibre \({ }^{\mathrm{TM}}\) from Mentor Graphics. The extracted parasitic information is included in the netlist in the form of large networks of passive resistors, capacitors and inductors connected to the transistors or other active objects of the circuit. Due to the large number of elements that they contain, such parasitic networks strongly constrain post-layout simulation both in terms of memory and CPU time. The Eldo Reduction capabilities allow to cope with this constraint by susbtituting such networks on the fly by approximately equivalent but smaller sized networks computed by the TICER reduction engine \({ }^{123}\). The quality of the approximation can be controlled by setting a maximum delay error, a maximum noise error and/or a cut-off frequency as explained in this chapter.

Not only back-annotated circuits may benefit from the savings in computer resources allowed by the Eldo Reduction but also some specific circuits. For instance, this is the case for power distribution networks having large portions of purely resistive networks.

The reduction methods available in Eldo are also, and primarily, available in the \(x\) Calibre extraction tool, and it is strongly recommended to activate the reduction of parasitics while performing extraction with Calibre \({ }^{\circledR} \times \mathrm{xC}^{\mathrm{TM}} / \mathrm{xL}\).

Nevertheless, even when the reduction of parasitic networks was performed in the extraction tool there may be some benefit in performing reduction in Eldo. This is clearly the case when the parasitics were generated to be valid over a frequency range that far exceeds the signal frequencies involved in the simulations to be performed. Using its reduction capabilities allows Eldo to take full benefit of reduction for each simulation individually while using parasitic networks valid over a possibly larger range of frequencies. Although this provides a convenient capability, it remains preferable and it is recommended to use different sets of extracted parasitics corresponding to the various frequency ranges of the simulations to be performed.

\footnotetext{
1. B. Sheehan, Branch Merge Reduction of RLCM networks, proceedings of the IEEE International Conference on Computer-Aided Design, 9-13 Nov. 2003, pp. 658-664.
2. B. Sheehan, TICER: Realizable Reduction of Extracted RC Circuits, proceedings of the IEEE International Conference on Computer-Aided Design, 7-11 Nov. 1999, pp. 200-203.
3. B. Sheehan, Realizable Reduction of RC Networks, IEEE Trans. Comput-Aided Design Integr. Circuits Syst., vol. 26, no. 8, pp. 1393-1407, Aug. 2007.
}

The primary advantages of reduction are:
- Results in smaller circuits, thus faster simulations.
- Requires less memory resources (uses less RAM and reduces swap space allocations).

\section*{Basic Reduction}

The easiest way of activating the Eldo Reduction is by using the generic . reduce ANALOG=YES \(\mid\) NO command. The mandatory YES or NO value of the boolean ANALOG parameter selects some default settings usually suitable for analog or digital-like circuits respectively. The latter ones refer to circuits with square signals and for which the accuracy on the signals amplitude and delay are less stringent than for pure analog circuits. You may optionally specify a maximum delay error, noise error or cut-off frequency for the reduction process.

By default the Eldo generic . Reduce analog=yes | NO command automatically activates a combination of reduction methods expected to be well suited for the circuit being reduced according to its topology. However, this automatic selection may induce some CPU and memory overhead and it is highly recommended that for large-sized backannotations the type of (parasitic) network to be reduced be specified using the REDUCE_NETWORK_TYPE option.

\section*{Advanced Reduction}

In addition to the generic . REDUCE ANALOG=yes \(\mid\) NO command some specific reduction commands for RLC or RC (. REDUCE TICER command), resistive-only reduction (. REDUCE ronly command) or coupling-capacitance reduction (. REDUCE CC command) are available. Together with the available reduction options they provide a full control of the reduction process.

\section*{Main Parameters Controlling the Reduction Process}

There are three main reduction parameters controlling the reduction methods activated by a generic . Reduce analog=yes|no command, or more advanced specific reduction commands, described in the dedicated sections of this chapter.

The noise error parameter is defined as the amount of change in noise amplitude relative to a full strength signal. The noise-error value is a ratio, a unitless floating number. The default value is 0.01 (corresponding to \(1 \%\) ) for the . REDUCE ANALOG=yES command and 0.05 (5\%) for the . Reduce analog=no command.

Hereafter default values for both . Reduce analog=yes and .reduce analog=no commands are denoted analog default values and digital-like default values respectively.

The delay error parameter refers to the timing delay threshold used for reduction. The delay error units are seconds. The analog default is \(0.5 \mathrm{e}-12\) (a half picosecond); the digital-like default is \(1.0 \mathrm{e}-12\) (one picosecond).

The cut-off frequency refers to the upper limit of the frequency band ranging from DC upwards over which the Eldo Reduction is requested to maintain accuracy of the simulation results computed using the reduced circuit, within the effective noise error and delay error margins, as compared to the simulation results that would be obtained with the original unreduced circuit. Refer to the TICER reduction command below for a more detailed explanation of this cut-off frequency parameter.

Since the members of this parameter triplet are interdependent at most two of them can be specified. Moreover, some of them-even if specified explicitly on the reduction commandmay be overridden according to parameters specified on some possibly conflicting reduction commands, according to the minimum frequency required to resolved the circuit input signals and possibly to the frequency range implied by the required simulation analyses as well. When such a situation happens, Eldo issues a warning indicating the effective value of the reduction parameter being modified.

\section*{Reduction Output}

Some statistics are printed to allow you to assess the efficiency of the reduction process using the default or specified parameter values (noise error, delay error and/or cut-off frequency). These statistics may change between two successive Eldo versions as a result of a permanent development process toward increasing reduction efficiency. Nevertheless the accuracy of the simulation results, relative to those of the original unreduced circuit, is preserved as long as the reduction cut-off frequency, noise error and delay error are set adequately.

\section*{Generic Reduction Command}

\section*{.REDUCE ANALOG}

This command actives a combination of TICER, RONLY and/or CC reduction methods expected to be well suited for the circuit being reduced.

\section*{Usage}
```

.REDUCE ANALOG=YES|NO

+ [DELAY_ERROR=value] [NOISE_ERROR=value]
.REDUCE ANALOG=YES NO
+ [FREQUENCY=value] [DELAY_ERROR=value]
.REDUCE ANALOG=YES|NO
+ [FREQUENCY=value] [NOISE_ERROR=value]

```

\section*{Description}

This generic command activates the Eldo Reduction using analog or digital-like default values. This command combines the effects of the . Reduce ticer or .reduce ronly commands and possibly the . Reduce cc command as well. The latter commands take precedence over the . Reduce analog=yes|no command if they are specified in the netlist.
At most two parameter values among delay_error, noise_error and frequency values may be specified. If a value is not specified for either, the default value is used.

The default value for frequency is computed accounting for the specified or default values of NOISE_ERROR and/or DELAY_ERROR, accounting for the circuit input signals and for the setup of the analyses to be simulated as well. When a conflict arises as a result of the specified parameter values, it is tentatively resolved by overriding either parameter value and an informative warning is issued.

Specific TICER, RONLY or CC reductions may be performed according to the related specific . Reduce commands present in the netlist.

\section*{Arguments}
- ANALOG=YES|NO

Mandatory parameter and value.
If YES, this parameter indicates to use the analog default values for the noise error, delay error or cut-off frequency parameter when they are not specified. This is the default behavior.

If NO, this parameter indicates to use the digital-like default values for the noise error, delay error or cut-off frequency parameter when they are not specified.
- DELAY_ERROR=value

Optional parameter and value specifying the timing delay threshold used for reduction. The delay units are seconds. The analog default is \(0.5 \mathrm{e}-12\) (a half picosecond); the digital-like default is \(1.0 \mathrm{e}-12\) (one picosecond).
- NOISE_ERROR=value

Optional parameter and value specifying the error threshold used for reduction. The noise error is defined as the amount of change in noise amplitude relative to a full strength signal. The noise value is a ratio, a unitless floating number. The analog default value is \(0.01(1 \%)\); the digital-like one is 0.05 (5\%).
- FREQUENCY=value

The optional frequency parameter controls which nodes in the circuit TICER can select for subsequent elimination; the tool selects nodes with time constants less than a fourth of the inverse frequency parameter.
Setting the frequency parameter a higher value results in larger (more R, C and Lelements) circuits having a wider bandwidth of accuracy.

Setting the frequency parameter a lower value results in more compression and an earlier roll-off in accuracy.
Calculate the frequency parameter value using the following formula:
frequency_value \(=\) tradeoff_value \(/\) transition_time_minimum
where:
tradeoff_value is a number between 4 and 10. A larger trade-off value results in a higher frequency parameter value and, consequently, more accurate and less aggressive reduction. transition_time_minimum is the shortest rise or fall time expected in the design. In general it can be estimated as a fifth of the design switching delay.
TICER reduction preserves the frequency response of the circuit from DC up to the specified frequency value. Consequently, the frequency parameter controls trading off compression with accuracy.

\section*{Example}
. REDUCE ANALOG=YES
Specifies that reduction will be done with the analog default values for delay_error ( 0.5 ps ) and NOISE_ERROR ( \(1 \%\) ).
```

.REDUCE ANALOG=NO

```

Specifies that reduction will be done with the digital-like default values for delay_error ( 1 ps ) and NOISE_ERROR (5\%).
```

.REDUCE ANALOG=YES DELAY_ERROR=5e-12 NOISE_ERROR=0.15

```

Specifies a reduction with a delay error of 5 picoseconds and a noise error of \(15 \%\).
```

.REDUCE ANALOG=YES DELAY_ERROR=5e-12

```

Shows how one of the optional parameters may be used. In this case the analog default value for NOISE_ERROR ( \(1 \%\) ) will be used together with the specified delay error.
.REDUCE ANALOG=NO NOISE_ERROR=0.1
Shows how one of the optional parameters may be used. In this case the default digital-like value for delay_error ( 1 ps ) will be used together with the specified noise error.

\section*{TICER Reduction Command .REDUCE TICER}

This command specifies to perform TICER reduction in a way that has little impact on circuit characteristics such as delay up to a specified frequency. By default TICER RLC reduction using branch merging or TICER RC reduction is activated according to the circuit topology. Either may be forced by specifying the REDUCE_NETWORK_TYPE option value to "RLC" or "RC" respectively.

\section*{Usage}
```

.REDUCE TICER FREQUENCY=value [ PORTMERGE [=value ]]

+ [ ANALOG=YES|NO ]
+ [ DELAY_ERROR=value | NOISE_ERROR=value ]

```

\section*{Description}

This command activates electrically-based reduction. The reduction compresses RLC or RC networks into equivalent ones although the topology may be entirely different.

Basic TICER does not move or alter ports (connections between RLC networks and the remaining elements of the circuit). Port merging enables TICER RLC reduction to achieve more reduction than it might otherwise by combining certain ports that normally would be kept separate. In practice, many RLC circuits-especially local networks-are "port bound" in the sense that they have relatively many ports and relatively few internal nodes. Often basic TICER cannot reduce these RLC networks much because it can only eliminate internal nodes. With port merging, TICER can eliminate ports as well by transferring the ports onto neighboring nodes. This gives TICER reduction greater flexibility and allows it to achieve more reduction.

\section*{Note}

It is especially important when using PORTMERGE to choose a correct setting for the TICER frequency parameter. If there are too many low-value resistors in the netlist, omit portmerge from the . Reduce ticer command or use a higher TICER cut-off frequency parameter value.

\section*{Note}

The default or specified noise-error and delay-error values are guess values that may be automatically modified to account for cut-off frequency and portmerge timing threshold values, that take precedence over them. In such a case a warning message is issued to inform you of the effective values of noise error and delay error used. These values are also printed at the beginning of the reduction statistics summary, along with the reduction cut-off frequency.

\section*{Arguments}
- FREQUENCY=value

The mandatory frequency parameter controls which nodes in the circuit TICER can select for subsequent elimination; the tool selects nodes with time constants less than a fourth of the inverse frequency parameter value.

Setting the frequency parameter a higher value results in larger (more \(\mathrm{R}, \mathrm{C}\) and L elements) circuits having a wider bandwidth of accuracy.

Setting the frequency parameter a lower value results in more compression and an earlier roll-off in accuracy.

Calculate the frequency parameter value using the following formula:
frequency_value \(=\) tradeoff_value \(/\) transition_time_minimum
where:
tradeoff_value is a number between 4 and 10. A larger trade-off value results in a higher frequency parameter value and, consequently, more accurate and less aggressive reduction.
transition_time_minimum is the shortest rise or fall time expected in the design. In general it can be estimated as a fifth of the design switching delay.

TICER reduction preserves the frequency response of the circuit from DC up to the specified cut-off frequency value. Consequently, the frequency parameter controls trading off compression with accuracy.
- PORTMERGE [=value]

An optional keyword that enables a more aggressive form of TICER reduction. This form combines ports whenever the change in timing is less than the specified value. The default timing tolerance is such that the impact on the time constants of ports is equivalent to that set by the reduction cut-off frequency for nodes. The default timing threshold value uses the following formula:
value \(=1 /(8 \times\) frequency \()\)
This parameter has no effect on TICER reduction alone when option
REDUCE_NETWORK_TYPE=RC is set.
- analog=yes | No

Optional parameter and value.
If YES, specifies to use the analog default values of delay error and noise error. This is the default.

If NO, specifies to use the digital-like default values of delay error and noise error.
- DELAY_ERROR=value

Optional parameter specifying the timing delay threshold used for reduction. The delay units are seconds. The analog default is \(0.5 \mathrm{e}-12\) (a half picosecond); the digital-like default is \(1.0 \mathrm{e}-12\) (one picosecond).

This parameter has no effect on TICER reduction alone when option REDUCE_NEWTORK_TYPE=RC is set.
- NOISE_ERROR=value

Optional parameter specifying the error threshold used for reduction. The noise error is defined as the amount of change in noise amplitude relative to a full strength signal. The value for noise error is a ratio, a unitless floating number. The analog default value is 0.01 ( \(1 \%\) ); the digital-like one is 0.05 (5\%).
This parameter has no effect on TICER reduction alone when option REDUCE_NEWTORK_TYPE=RC is set.

\section*{Example}
. REDUCE TICER FREQUENCY=5GHz
Specifies a basic TICER reduction (without aggressive port merging) preserving accuracy of the frequency response from DC up to 5 GHz , and not using any default value of noise error or delay error.
. REDUCE TICER FREQUENCY=1GHz PORTMERGE=1ps ANALOG=YES
Specifies a TICER reduction with a 1 gigahertz cut-off frequency and aggressive portmerge reduction using a timing threshold of 1 picosecond, and also using the analog default values of noise error and delay error.

\section*{Reduction Command for Resistive Networks .REDUCE RONLY}

This command reduces resistive-only networks by eliminating all internal nodes.

\section*{Usage}
.REDUCE RONLY [SPARSIFY = YES|NO]

\section*{Description}

The . reduce ronly command operates only on resistive networks, ones that do not include capacitance or inductance. It is most effective on networks with few ports and many internal nodes.

The R-Only operation reduces resistive networks so that they are electrically equivalent to the original ones, but the topology may be entirely different. The effective resistance between ports is preserved.
With the sparsify optional parameter is set to YES, the circuit is further reduced by eliminating some resistors and adjusting the values of others to compensate.

The R-Only reduction is more aggressive than . REDUCE ANALOG=Yes \(\mid\) No, making it especially useful for large resistive networks, such as power distribution networks, that might otherwise exceed available computer resources. When both reduction commands are specified in the netlist, . Reduce ronly is applied to pure resistive networks and . Reduce ticer / .reduce cc to the other networks.

\section*{Arguments}
- SPARSIFY=Yes|no

Optional keyword and value.
If YES, directs that the resistive networks should be further reduced by combining resistors.
If NO, this resistor combining reduction will not be performed. This is the default behavior.

\section*{Example}
. REDUCE RONLY
Specifies that reduction will be done on a resistive only network.

\section*{Reduction Command for Coupled Capacitances .REDUCE CC}

This reduction command controls reduction of coupled capacitance between RLC or RC nets based on total capacitance.

\section*{Usage}
```

.REDUCE CC

+ ABSOLUTE=value | RATIO=value | ABSOLUTE=value RATIO=value
+ [SCALE=value]

```

\section*{Description}

This reduction command controls reduction of coupled capacitance between RLC or RC nets based on total capacitance.

When both an absolute threshold value and a relative threshold ratio value are specified, both conditions must be true before the coupled capacitance is grounded.

Note
The CC reduction occurs before the TICER reduction implied by a . REDUCE ANALOG=NO command, and after the TICER reduction implied by a .REDUCE ANALOG=YeS command.

\section*{Arguments}
- ABSOLUTE=value

Keyword and absolute threshold value. If the total coupling capacitance between a pair of RLC or RC nets is less than the specified threshold value, that coupling is applied as grounded capacitances to both nets.
- RAtio=value

Keyword and relative threshold value as a number between 0 and 1. The total coupled capacitance between two RLC or RC nets is compared to the total capacitance of each individually. If for both nets the coupled capacitance accounts for less than the relative threshold ratio (expressed as a decimal) of the total net capacitance, that coupling is applied as grounded capacitances for both nets.
- SCALE=value

Optional keyword and value that applies the scale factor to the reduce capacitances before grounding. Only the coupled capacitances that are converted to grounded capacitance are scaled; the other capacitances are not modified. By default, the scale value is 1.0 .

\section*{Example}

The RATIO decoupling condition is met when the total coupling capacitance between two nets is less than the specified percent of both. For example, net A and net B are coupled by 26 fF . The total capacitance (intrinsic and coupled) on net A is 250 fF and on net B is 300 fF .

The following reduction command is used:
. REDUCE CC RATIO=0.1
Then the A-B coupling will not be grounded because although 26 fF is less than \(10 \%\) of net B's 300 fF , it is greater than \(10 \%\) of net A's 250 fF .

\section*{Reduction Options}

Some options are provided with the aim of helping the reduction process to achieve greater efficiency or controlling the topological impact of reduction on the circuit.

\section*{Specifying the Network Type for Reduction}

\section*{Option Syntax}
. option REDUCE_NETWORK_TYPE = RLC | RC | RONLY

\section*{Description}

This option specifies the type of networks to be reduced:
- RLC for (parasitic) networks containing resistors, capacitors and inductors. This is the default.
- RC for (parasitic) networks with only resistors and capacitors, no inductors.
- ronly for pure resistive networks, no capacitors nor inductors.

Note
It is strongly recommended to set this option according to the parasitic network type for large-sized backannotations.

\section*{Note}

This option may be used to control the reduction methods selected by the . REDUCE
ANALOG=YES \(\mid\) NO command, by overriding the default network type selected according to the circuit topology.

\section*{Controlling the Effects of Reduction on Circuit Topology}

\section*{Option Syntax}
. option REDUCE_MAX_RES=value
.option REDUCE_MAX_CAP=value
.option REDUCE_MAX_IND=value

\section*{Description}

This option specifies the maximum value of resistors, capacitors and inductors respectively, that are eligible for reduction. That is, elements with values greater than the specified value(s) will not be removed by reduction.

\section*{Note}

These options may be used to avoid the removal of some resistors, capacitors and inductors that are not parasitics but are part of the active circuitry. The characteristics of some unstable circuits, such as oscillators, may indeed be affected by the removal of such elements.

\section*{Option Syntax}
.option REDUCE_KEEP_OUTPUTS = YES|NO

\section*{Description}

If yes, the default, this option ensures that no required output becomes unavailable as a result of reduction. If no, it allows reduction to remove some nodes and/or Rs, Cs, Ls even if they are related to some requested outputs.

\section*{Note}


Setting option Reduce_keep_outputs=no provides a convenient way for assessing whether reduction is hampered by a large number of requested outputs. In such a case, the options reduce_keep_node and reduce_keep_inst may be added to selectively recover the availability of some missing outputs.

\section*{Option Syntax}
. option REDUCE_KEEP_NODE=name

\section*{Description}

This option prevents the specified node from being eliminated by reduction. Double quotes are mandatory. By default, nodes related to output statements and nodes connected to devices other than a resistor, a capacitor or an inductor are not removed, unless option
REDUCE_KEEP_OUTPUTS=NO is set.

\section*{Option Syntax}
```

    .option REDUCE_KEEP_INST=name
    ```

\section*{Description}

This option prevents the specified resistor, capacitor or inductor instance from being eliminated by reduction. By default, instances related to output statements are not removed unless option REDUCE_KEEP_OUTPUTS=NO is set.

\section*{Chapter 16 Integral Equation Method (IEM)}

\section*{Introduction}

The Integral Equation Method (IEM) is a simulation algorithm developed for transient analog circuit simulation. With some circuits, IEM provides better performance than classic algorithms based on the Newton-Raphson method combined with a multi-step discretization scheme (for example Backward Euler, trapezoidal, gear, and so on).

In some cases, IEM may perform better than Newton methods in terms of stability and accuracy, which has a favorable incidence on speed. The improvements appear particularly for circuits requiring high precision or those which exhibit tight coupling or stability problems.

IEM's performance enhancement derives from the use of a semi-analytic approach combined with efficient numerical techniques.

\section*{Application Domains}

IEM is invoked for TRANSIENT analysis of ANALOG circuits only. DC and AC analyses can only be performed using Newton-Raphson methods.

In case Eldo works together with another simulation kernel, digital or analog, then IEM is not supported.

\section*{Circuit Elements Supported-Limitations}

As a rule, all circuit elements accepted by Eldo are supported by IEM except objects described by HDL-A, FAS or GUDM.

To be more explicit, elements actually supported by IEM are listed below.
- MOS models

Table 16-1. IEM Supported MOS Models
\begin{tabular}{|l|l|l|l|l|l|}
\hline MERCK2 & MERCK3 & MERCK4 & BERK1 & BERK2 & BERK3 \\
\hline BSIM1 & BSIM2 & STMOS1 & STMOS3 & EKV & MISNAN \\
\hline BSIM3 & CSEM & BSIM3V3 & MOTOROLA & MOSP9 & \\
\hline
\end{tabular}
- BJT models

Table 16-2. IEM Supported BJT Models
\begin{tabular}{|l|l|l|l|l|l|}
\hline BERKBIP & STBIP & & & & \\
\hline
\end{tabular}
- Diodes

Table 16-3. IEM Supported Diode Models
\begin{tabular}{|l|l|l|l|l|l|}
\hline BERKDIO & ELDIO2 & TUNNELD & STDIO & STFOWL & STMIS \\
\hline JUNCAP & & & & & \\
\hline
\end{tabular}
- All other electrical device models, except:
- \(\mathrm{R}, \mathrm{L}\), and C defined by the value statement
- S and Z domain filters
- All independent or controlled sources are supported, except:
- Controlled sources defined by either the value or table statements (Note: Linear and polynomial controlled sources are supported)
- All digital and mixed-signal macromodels are supported
- Only comparator and delay elements are supported among analog macromodels
- Only the switch element is supported among switched capacitor macromodels
- Accusim magnetic models are supported but not those of Eldo.

In case a circuit or block contains an element not supported by IEM, this circuit or block is simulated using Newton-Raphson and a warning message is issued.

\section*{Use of IEM, Tolerance Parameters}

The following simulation algorithms may be used on a circuit depending on the setting of the . OPtION line in the netlist and/or on the use of the (ANALOG) attribute on subcircuits:
- .OPTION NEWTON

In this case the whole circuit is simulated in a single block, using the Newton method. Default.
- .OPTION IEM

In this case the whole circuit is simulated in a single block, using IEM.
- . OPtion blocks=NEWTON

In this case, the circuit is partitioned (whenever possible) into one or more blocks. Simulation inside each block is performed using the Newton method and relaxation is
undertaken between blocks using OSR. OSR is also used to simulate the non-Newton part of the circuit.
- . OPTION BLOCKS=IEM

In this case, the circuit is partitioned (whenever possible) into one or more blocks. Simulation inside each block is performed using IEM and relaxation is undertaken between blocks using OSR. OSR is also used to simulate the non-IEM part of the circuit.

\section*{Note}
\(\square\) The default simulation option is Newton, i.e. .OPTION=NEWTON
If a block contains either a GUDM, HDL-A or FAS model, then simulation inside that particular block will be performed using the Newton method. If no IEM blocks are created (because all blocks contain unsupported objects or the circuit is loosely coupled and can be simulated with OSR) then the IEM option is removed and a warning message is issued.
reltol and vntol parameters can be used in the same way as for SPICE-like simulators. These control both convergence of iteration loops and step size.

Note
For Newton-Raphson, reltol does not control the step size.

If reltol or vntol are not explicitly specified in the netlist, then eps can be used to control their values, as follows:
- Reltol \(=\left(1.0 \times 10^{-9} \times \text { EPS }\right)^{1 / 4}\)
reitol is then limited in the range \(1.0 \times 10^{-2}\) to \(1.0 \times 10^{-5}\)
- Vntol \(=\left(1.0 \times 10^{-7} \times \text { EPS }\right)^{1 / 2}\)
vNTOL is then limited in the range \(1.0 \times 10^{-3}\) to \(1.0 \times 10^{-9}\)
For IEM, the option LVLtim is by default set to 2, i.e. truncation error is used to control the time step. It is possible to set lvitim=3 in the netlist, which will also allow the truncation error to control the time step. Additionally, it will impose calculated points at trrint values in the . TRAN command. Other settings of lvitim are not allowed since they produce less accurate results which would be meaningless with IEM.

All other SPICE compatible options (for example Abstol, itol, and so on) behave in the same way as for Newton-Raphson. This of course does not include integration scheme options (be, trap, gear, ...) which do not apply to IEM.

In order to maintain compatibility with previous Eldo versions and Newton usage, eps may still be used in the Eldo sense, i.e. as a means to control all precision parameters.

\section*{Efficient Usage of IEM}

This section describes some details to help users achieve the best accuracy and performance results with IEM, used alone or in combination with OSR.
- IEM alone (. Option IEM)

As already discussed above, this setup allows IEM to simulate the whole circuit in a single block. This is required for all-analog designs, or at least when the analog part of the circuit is much larger than the logic circuitry (i.e. approximately \(75 \%\) of devices or more). This option is particularly recommended for circuits requiring high precision and/or those manifesting stability problems. IEM intrinsically gives very good accuracy and doesn't require tightening of accuracy parameters. Hence, the default eps value is usually enough to achieve high quality simulation results. Lowering EPS will give even higher precision, but at the expense of CPU time.
- IEM + OSR (. OPtion blocks=IEM)

This setup allows Eldo to partition the circuit, assigning tightly coupled blocks into IEM, the remaining part being simulated with OSR. By default, MOS and grounded capacitors are assigned to OSR, hence it is recommended to use this setup in conjunction with a correct imposition of the attribute (ANALOG) for relevant circuits. This way, BJTs, resistors, and all MOS analog subcircuits will be simulated by IEM while other MOS blocks will be considered as logic ones and efficiently simulated by OSR (whenever possible).

As usual, it is possible to increase accuracy by reducing eps, however, as in all-IEM simulation this is not particularly recommended.

\section*{Note}

The combination of IEM (a highly precise algorithm) with OSR (a fast but less precise algorithm) may not be justified in some cases.

\section*{Examples for IEM}

\section*{Introduction}

This section demonstrates the advantages of IEM, using the following set of examples:
- Stability
- bjtinv_iem.cir and bjtinv_nrm.cir
- ivdd_iem.cir and ivdd_nrm.cir

Newton-Raphson ( nrm ) versions are included for comparison with the *iem.cir files.
- Accuracy
- oscil_iem.cir, oscil_nrm.cir and oscil_ref.cir
- moyl_iem.cir, moyl_nrm.cir and moyl_ref.cir

Newton-Raphson ( \(\mathbf{n r m}\) ) and reference ( \(\mathbf{r e f}\) ) versions are included for comparison with the *iem.cir files.
- Speed
- ladder_iem.cir and ladder_nrm.cir
- opamp_5pin_iem.cir and opamp_5pin_nrm.cir

Newton-Raphson (nrm) versions are included for comparison with the *iem.cir files. The listings for these examples can be found in the following directory included with your software:
```

\$MGC_AMS_HOME/examples/eldo

```

\section*{Note}

For more examples of using Eldo please refer to the Examples appendix and the Tutorials chapter.

\section*{Stability}

IEM is inherently stable as opposed to, for example, the Trapezoidal scheme which may sometimes exhibit numerical instabilities. These instabilities can be suppressed by reducing tolerances. Backward-Euler scheme also offers numerical damping but tolerances should be greatly decreased in order to obtain an acceptable precision. In both cases, this increases the CPU time. For IEM, these numerical instabilities do not appear even at default precision. The following examples (bjtinv_iem.cir and ivdd_iem.cir) demonstrate this effect.

\section*{Example 1—bjtinv}

\section*{Complete Netlist}

\section*{Note}

The netlist is also provided as a Newton-Raphson version (bjtinv_nrm.cir) in the examples directory for comparison. The netlist is identical to bjtinv_iem.cir with the exception of .OPtion newton selected as opposed to .OPtion iem.
```

bjtinv_iem.cir
vcc 5 0 dc 5.
vin 1 0 pulse(0 5 10ns 40ns 40ns 110ns 300ns)
.subckt inv 5 1 6

```
```

q1 3 2 0 x33
q2 6 4 0 x33
rc1 5 3 1k
rc2 5 6 1k
rb1 1 2 10k
rb2 3 4 10k
.ends inv
x1 5 1 6 inv
x2 5 6 10 inv
x3 5 10 11 inv
x4 5 11 12 inv
x5 5 12 13 inv
x6 5 13 14 inv
.print tran v(1) v(11) v(14)
.plot tran v(1) v(x2.3) v(11) v(14)
.tran 2ns 300ns
.model x33 npn(bf=80 rb=100 va=50 tf=.3e-9 tr=6.e-9)
.option iem accusim2
.end

```

\section*{Simulation Results}

Figure 16-1 compares the waveform produced by the Newton-Raphson method (shown in green) compared with the waveform produced by the IEM method (shown in yellow).

Figure 16-1. Example 1-bjtinv


\section*{Example 2—ivdd}

\section*{Note}

Included in this directory are ivdd_xxx.cir examples which are intended for use with Eldo-ST. Eldo-ST is available for STMicroelectronics licensees only. Non-license holders may still simulate these examples but multiple warning messages will be generated.

\section*{Complete Netlist}
\(\qquad\)
```

ivdd_iem.cir
.option XA= 1.500000e-06
*-----------------------------------------------------------------* Main
Circuit Netlist:
*------------------------------------------------------------------C25 Z GND
8.5188e-16
C24 Z VDD 8.1332e-16
C23 N2 GND 6.3258e-15
C22 N2 VDD 6.79986e-15
C21 N2 Z 4.05478e-15
C20 A GND 9.072e-16
C19 A VDD 8.3745e-16
C18 A N2 8.05086e-16
M9 VDD A N2 VDD EP3 W=1.05571e-05 L=5e-07 AD=1.14175e-11

+ AS=1.1425e-11 PD=3.3e-06 PS=1.31e-05
M16 Z N2 VDD VDD EP3 w=1.07571e-05 L=5e-07 AD=5.22e-12
+ AS=1.0495e-11 PD=1.3e-06 PS=2.7e-06
M14 Z N2 VDD VDD EP3 W=1.07571e-05 L=5e-07 AD=5.22e-12
+ AS=1.0495e-11 PD=1.3e-06 PS=2.7e-06
M12 Z N2 VDD VDD EP3 W=1.07571e-05 L=5e-07 AD=5.22e-12
+ AS=1.0495e-11 PD=1.3e-06 PS=2.7e-06
M10 Z N2 VDD VDD EP3 W=1.07571e-05 L=5e-07 AD=5.22e-12
+ AS=1.14175e-11 PD=1.3e-06 PS=3.3e-06
M17 VDD N2 Z VDD EP3 W=1.07571e-05 L=5e-07 AD=1.7695e-11
+ AS=5.22e-12 PD=1.59e-05 PS=1.3e-06
M15 VDD N2 Z VDD EP3 W=1.07571e-05 L=5e-07 AD=1.0495e-11
+ AS=5.22e-12 PD=2.7e-06 PS=1.3e-06
M13 VDD N2 Z VDD EP3 W=1.07571e-05 L=5e-07 AD=1.0495e-11
+ AS=5.22e-12 PD=2.7e-06 PS=1.3e-06
M11 VDD N2 Z VDD EP3 W=1.07571e-05 L=5e-07 AD=1.0495e-11
+ AS=5.22e-12 PD=2.7e-06 PS=1.3e-06
M0 GND A N2 GND EN3 W=5.4e-06 L=5e-07 AD=5.9025e-12 AS=6e-12
+ PD=3.4e-06 PS=8.4e-06
M7 Z N2 GND GND EN3 W=5.25711e-06 L=5e-07 AD=2.87e-12
+ AS=5.445e-12 PD=1.3e-06 PS=3.2e-06
M5 Z N2 GND GND EN3 W=5.25711e-06 L=5e-07 AD=2.87e-12
+ AS=5.445e-12 PD=1.3e-06 PS=3.2e-06
M1 Z N2 GND GND EN3 W=5.25711e-06 L=5e-07 AD=2.87e-12
+ AS=5.9025e-12 PD=1.3e-06 PS=3.4e-06
M3 Z N2 GND GND EN3 W=5.25711e-06 L=5e-07 AD=2.87e-12
+ AS=5.445e-12 PD=1.3e-06 PS=3.2e-06
M8 GND N2 Z GND EN3 W=5.25711e-06 L=5e-07 AD=9.645e-12
+ AS=2.87e-12 PD=1.14e-05 PS=1.3e-06
M6 GND N2 Z GND EN3 W=5.25711e-06 L=5e-07 AD=5.445e-12
+ AS=2.87e-12 PD=3.2e-06 PS=1.3e-06
M4 GND N2 Z GND EN3 W=5.25711e-06 L=5e-07 AD=5.445e-12
+ AS=2.87e-12 PD=3.2e-06 PS=1.3e-06
M2 GND N2 Z GND EN3 W=5.25711e-06 L=5e-07 AD=5.445e-12
+ AS=2.87e-12 PD=3.2e-06 PS=1.3e-06
******************************************************************
.model en3
nmos level=3
+ dmut = 1.474 dvt =-0.0011
+ eox = 11.3n dl = 0.130u dw = -0.100u
+ vt0 = 0.540 kb1 = 0.624 kb2 = 0.690
+ phil = 0.831 vc = 1.221 k0 =0.654E-04
+tg=0.064 racc = 411.2u tw = -0.001u
+ a2 = -0.0074u a3 = -0.076u a1 = -0.260u

```
```

+ b2 = 0.004u b3 = 0.032u b1 = 0.055u
+ del= 0.294 gl = -0.255u gw = 0.002u
+ delvg= -0.040 glvg = 0.152u gwvg = 0.001u
+ ke =0.250E+08 lo = 1.977u eps = 0.018u
+ n1 = 0.330
+ bn =0.455E+08
+ cjp=2.90e-10
+ rec=0.04u
+ ip=4.3e-09
.model ep3
+ pmos level=3
+ dmut = 1.330 dvt =-0.0010
+ eox = 11.3n dl = 0.140u dw = -0.10u
+ vt0 = 0.600 kb1 = 0.680 kb2 = 0.680
+ phi1 = 0.829 vc = 0.000 k0 =0.152E-04
tg=0.122 racc = 1071.2u tw = -0.002u
+ a2 = -0.036u a3 = -0.154u a1 = -0.154u
+ b2 = 0.009u b3 = 0.036u b1 = 0.036u
del=0.311 gl = -0.191u gw = 0.010u
+ delvg=-0.036 glvg = 0.040u gwvg = -0.011u
+ ke =0.370E+08 lo = 0.574u eps = 0.052u
+ n1 = 0.432 n2 = 1.069 an =0.219E+06
bn =0.734E+08 cjs=7.93e-04 mjs=0.33
+ cjp=2.29e-10 mjp=0.14 cjc=1.1e-10
+ rec=0.04u recl=0.1u is=8.00e-04
+ ip=4.0e-09 xti=3.0 nd=2.0
********************************************
Vdd vdd 0 dc 3.6
Vin A O pwl (0 0 4n 0 4.25n 3.6 9n 3.6 9.25n 0)
*******************************************
Vdum Z Z1 dc 0
*********************************************
Cload Z1 0 3.2p
*********************************************
.temp 25
.tran 0.005n 32n
.connect 0 GND
.option accusim2
.option iem !stable
*.option newton !trapezoidal exhibits numerical oscillations
.plot tran i(vdd)
.plot tran i(vdum)
.defwave wivdd=abs(i(vdd))
.defwave wivdum=abs(i(vdum))
.extract integ(w(wivdd))
.extract integ(w(wivdum))
.end

```

\section*{Simulation Results}

Figure 16-2 compares the waveform produced by the Newton-Raphson method (shown in yellow) compared with the waveform produced by the IEM method (shown in green).

Figure 16-2. Example 2—ivdd


\section*{Accuracy}

The precision is measured by comparing the results for each algorithm to a reference. The reference can be obtained using either of the two algorithms, by setting extremely low values on tolerance parameters. By default, IEM gives results at relatively high precision. In order to attain the same accuracy using Newton-Raphson, tolerance parameters should be tightened, which results in an increase in the CPU. The performance gain is measured by the CPU ratio between both algorithms when the output results are at the same level of accuracy.

\section*{Example 3—oscil}

For this oscillator, a jitter lower than \(2 \%\), can be obtained by IEM at default settings, or by Newton-Raphson at EPS=3.0e-7. At this level of accuracy, the speed-gain for IEM is about \(3 \times\).

Complete Netlist
Note
The netlist file is also provided as Newton-Raphson and reference versions (oscil_nrm.cir
and oscil_ref.cir respectively) in the examples directory. oscil_ref.cir is the reference
model to which the iem and nrm circuits are compared. The netlists are identical to
oscil__em.cir with the exception of .OPTION NEWTON selected for oscil_nrm.cir and
.OPTION NEWTON EPS=1.e-8 selected for oscil_ref.cir.
oscil_iem.cir
.MODEL PBSIM2 PMOS
\(+\mathbf{T N O M}=2.70000 \mathrm{E}+01\)
VDD \(=5.00000 \mathrm{E}+00\)
JS \(=2.00000 \mathrm{E}-06\)
\(+\mathbf{C G D O}=2.00000 \mathrm{E}-10\)
\(+\mathbf{M J}=4.30000 \mathrm{E}-01\)
CJ=3.80000E-04
+ DW=2.15737E-01
LNO \(=0.00000 \mathrm{E}+00\)
LNB \(=0.00000 \mathrm{E}+00\)
LND=0.00000E+00
LPHI=1.66784E+00
LMUOB \(=0.00000 \mathrm{E}+00\)
LK1 \(=0.00000 \mathrm{E}+00\)
LK2 \(=0.00000 \mathrm{E}+00\)
LETAO=2.74604E-02
LU10=2.66063E-01
LVFB \(=-2.01651 \mathrm{E}+00\)
LETAB \(=0.00000 \mathrm{E}+00\)
LU1B=0.00000E +00
LMU20=1.75239E+00
LMU2B \(=0.00000 \mathrm{E}+00\)
LMU30 \(=-9.23397 \mathrm{E}+0\)
LMUSO \(=9.17775 \mathrm{E}+00\)
LMUSB \(=0.00000 \mathrm{E}+00\)
LMU2G=0.00000E +00
LMU3B \(=0.00000 \mathrm{E}+00\)
LMU3G \(=0.00000 \mathrm{E}+00\)
LMU40=7.86998E-01
LMU4B=0.00000E+00
LMU4G=0.00000E+00
LUAO \(=2.68543 \mathrm{E}-01\)
LUAB \(=0.00000 \mathrm{E}+00\)
LUBO = - \(1.08792 \mathrm{E}-02\)
LUBB \(=0.00000 \mathrm{E}+00\)
LU1D=0.00000E+00
LVGHIGH \(=0.000 \mathrm{E}+00\)
LVOFO \(=0.00000 \mathrm{E}+00\)
LVOFB \(=0.00000 \mathrm{E}+00\)
LVOFD \(=0.00000 \mathrm{E}+00\)
LAIB \(=0.00000 \mathrm{E}+00\)
\(\mathbf{L B I B}=0.00000 \mathrm{E}+00\)
+ LVGLOW \(=0.000 \mathrm{E}+00\)
\(\mathbf{B E X}=-1.50000 \mathrm{E}+00\)
LAIO= 1.03485E-01
level=11
RSH=6.50000E+01
VGG=5.00000E+00
XPART \(=0.00000 \mathrm{E}+00\)
CGBO \(=0.00000 \mathrm{E}+00\)
PBSW=0. \(10000 \mathrm{E}+00\)
CJSW=1.20000E-10
MU0 \(=4.88029 \mathrm{E}+02\)
WNO \(=0.00000 \mathrm{E}+00\)
\(\mathbf{W N B}=0.00000 \mathrm{E}+00\)
WND \(=0.00000 \mathrm{E}+00\)
WPHI \(=-3.12807 \mathrm{E}-01\)
WMUOB \(=0.00000 \mathrm{E}+00\)
WK1 \(=0.00000 \mathrm{E}+00\)
WK2 \(=0.00000 \mathrm{E}+00\)
WETAO \(=0.00000 \mathrm{E}+00\)
WU10 \(=0.00000 \mathrm{E}+00\)
WVFB=4.68098E-01
WETAB \(=0.00000 \mathrm{E}+00\)
WU1B=0.00000E+00
WMU20 \(=0.00000 \mathrm{E}+00\)
WMU2B=0.00000E+00
WMU30 \(=0.00000 \mathrm{E}+00\)
WMUSO \(=0.00000 \mathrm{E}+00\)
WMUSB \(=0.00000 \mathrm{E}+00\)
WMU2G=0.00000E+00
WMU3B \(=0.00000 \mathrm{E}+00\)
WMU3G \(=0.00000 \mathrm{E}+00\)
WMU40 \(=0.00000 \mathrm{E}+00\)
WMU4B \(=0.00000 \mathrm{E}+00\)
WMU4G=0.00000E+00
WUAO \(=-5.76159 \mathrm{E}-02\)
WUAB \(=0.00000 \mathrm{E}+00\)
WUBO \(=1.58744 \mathrm{E}-03\)
WUBB \(=0.00000 \mathrm{E}+00\)
WU1D \(=0.00000 \mathrm{E}+00\)
WVGHIGH \(=0.000 \mathrm{E}+00\)
WVOFO \(=0.00000 \mathrm{E}+00\)
WVOFB \(=0.00000 \mathrm{E}+00\)
WVOFD \(=0.00000 \mathrm{E}+00\)
WAIB \(=0.00000 \mathrm{E}+00\)
WBIB \(=0.00000 \mathrm{E}+00\)
WVGLOW \(=0.0000 \mathrm{E}+00\)
TCV \(=1.00000 \mathrm{E}-03\)
\(\mathrm{WAIO}=0.00000 \mathrm{E}+00\)
\(\mathbf{T O X}=1.50000 \mathrm{E}-02\)
\(\mathrm{VBB}=-5.00000 \mathrm{E}+00\)
CGSO \(=2.00000 \mathrm{E}-10\)
\(\mathrm{PB}=6.75000 \mathrm{E}-01\)
MJSW \(=4.30000 \mathrm{E}-01\)
DL=2.75240E-01
\(\mathbf{N O}=1.40000 \mathrm{E}+00\)
\(\mathbf{N B}=5.00000 \mathrm{E}-01\)
\(\mathbf{N D}=0.00000 \mathrm{E}+00\)
PHI \(=7.71089 \mathrm{E}-01\)
MUOB \(=0.00000 \mathrm{E}+00\)
\(\mathbf{K 1}=8.10175 \mathrm{E}-01\)
\(\mathbf{K 2}=4.67768 \mathrm{E}-02\)
ETAO \(=-1.78327 \mathrm{E}-02\)
U10=-1.46747E-02
VFB \(=-9.74625 \mathrm{E}-01\)
\(\mathbf{E T A B}=0.00000 \mathrm{E}+00\)
\(\mathrm{U} 1 \mathrm{~B}=0.00000 \mathrm{E}+00\)
MU20 \(=1.32844 \mathrm{E}+00\)
MU2B \(=0.00000 \mathrm{E}+00\)
MU30 \(=1.29954 \mathrm{E}+00\)
MUSO \(=5.30129 \mathrm{E}+02\)
MUSB \(=0.00000 \mathrm{E}+00\)
MU2G=-4.77583E-01
MU3B \(=0.00000 \mathrm{E}+00\)
MU3G=1.17696E+00
MU40 \(=-8.24961 \mathrm{E}-01\)
MU4B \(=0.00000 \mathrm{E}+00\)
MU4G=-1.19857E-01
UAO \(=2.89822 \mathrm{E}-02\)
UAB \(=-1.12017 \mathrm{E}-02\)
\(\mathrm{UBO}=1.22936 \mathrm{E}-02\)
\(\mathrm{UBB}=2.34752 \mathrm{E}-04\)
U1D \(=0.00000 \mathrm{E}+00\)
VGHIGH=2.00000E-01
VOFO \(=1.80000 \mathrm{E}+00\)
VOFB \(=0.00000 \mathrm{E}+00\)
VOFD \(=0.00000 \mathrm{E}+00\)
AIB \(=0.00000 \mathrm{E}+00\)
BIB \(=0.00000 \mathrm{E}+00\)
VGLOW=-1. \(50000 \mathrm{E}-01\)
DELL \(=0.00000 \mathrm{E}+00\)
AIO \(=-2.70194 \mathrm{E}-02\)
BIO \(=6.95477 \mathrm{E}-01\)
```

+ LBIO= 5.20197E-01 WBIO= 0.00000E+00
.MODEL NBSIM2 NMOS level=11
+ TNOM=2.70000E+01
+ VDD=5.00000E+00
+ JS=2.00000E-06
+ CGDO=2.00000E-10
+ MJ=4.30000E-01
+CJ=3.80000E-04
+ DW=2.15737E-01
+ NO=0.00000E+00
+ LNB=0.00000E+00
+ LND=0.00000E+00
+ LPHI=1.66784E+00
+ LMUOB=0.00000E+00
+ LK1=0.00000E+00
+ LK2=0.00000E+00
+ LETAO=2.74604E-02
+ LU10=2.66063E-01
+ LVFB=-2.01651E+00
+ LETAB=0.00000E+00
+ LU1B=0.00000E+00
+ LMU20=1.75239E+00
+ LMU2B=0.00000E+00 WMU2B=0.00000E+00 MU30=1.29954E+00
+ LMU30=-9.23397E+00 WMU30=0.00000E+00 MUSO=5.30129E+02
+ LMUSO=9.17775E+00 WMUSO=0.00000E+00 MUSB=0.00000E+00
+ LMUSB=0.00000E+00 WMUSB=0.00000E+00 MU2G=-4.77583E-01
+ LMU2G=0.00000E+00 WMU2G=0.00000E+00 MU3B=0.00000E+00
+ LMU3B=0.00000E+00 WMU3B=0.00000E+00 MU3G=1.17696E+00
+ LMU3G=0.00000E+00 WMU3G=0.00000E+00 MU40=-8.24961E-01
+ LMU40=7.86998E-01 WMU40=0.00000E+00 MU4B=0.00000E+00
+ LMU4B=0.00000E+00 WMU4B=0.00000E+00 MU4G=-1.19857E-01
+ LMU4G=0.00000E+00 WMU4G=0.00000E+00
LUAO=2.68543E-01 WUAO=-5.76159E-02
+ LUAB=0.00000E+00 WUAB=0.00000E+00
LUB0=-1.08792E-02
LUBB=0.00000E+00
LU1D=0.00000E+00
LVGHIGH=0.000E+00
LVOFO=0.00000E+00
LVOFB=0.00000E+00
LVOFD=0.00000E+00
+ LAIB=0.00000E+00
+ LBIB=0.00000E+00
+ LVGLOW=0.0000E+00
+ BEX=-1.50000E+00 TCV=1.00000E-03 AIO=-2.70194E-02
+ LAIO= 1.03485E-01 WAIO = 0.0000E+00 BIO= 6.95477E-01
+ LBIO= 5.20197E-01 WBIO = 0.0000E+00
Vdd vdd 0 dc 5
Vss vss 0 dc 0
.subckt inv in out vss vdd
r1 vdd vdd1 10
r2 vss vss1 10
M1 out in vss1 vss nbsim2 L=2U W=6U AD=90E-12 AS=90E-12 PD=24u
+ PS=24u
M2 out in vdd1 vdd pbsim2 L=2U W=10U AD=90E-12 AS=90E-12
+ PD=24u PS=24u
.ends inv

```
```

Xin1 in1 out1 vss vdd inv
cl out1 0 0.1f
xin2 out1 out2 vss vdd inv
c5 out2 0 0.1f
xin3 out2 out3 vss vdd inv
c2 out3 0 0.1f
xin4 out3 out4 vss vdd inv
c3 out4 0 0.1f
Xin5 out4 in1 vss vdd inv
c4 in1 0 0.1f
.tran 1n 100n uic
.ic v(out1)=5 v(out2)=0 v (out3)=5
.plot tran v(out1)
.plot tran v(out2)
.plot tran v(out3)
.plot tran v(out4)
.option accusim2
.option iem
.end

```

\section*{Simulation Results}

Figure 16-3 compares the waveform produced by the Newton-Raphson method (shown in yellow) compared with the waveform produced by the IEM method (shown in green) and the waveform produced by the reference model (shown in blue).

Figure 16-3. Example 3-oscil


\section*{Example 4—moy1}

The matching considerations in transistor current sources are showed in this circuit. By default, IEM gives an error in the average current difference of 32 nA . The same precision is attained by Newton-Raphson at EPS=1.0e-6. At this level the speed-gain for IEM is about \(2 \times\).

\section*{Complete Netlist}

\section*{Note}

The netlist file is also provided as Newton-Raphson and reference versions (moyl_nrm.cir and moyl_ref.cir respectively) in the examples directory. moy1_ref.cir is the reference model to which the iem and nrm circuits are compared. The netlists are identical to moyl_iem.cir with the exception of . OPTION NEWTON selected for moyl_nrm.cir and .OPTION NEWTON EPS=1.e-8 selected for moyl_ref.cir.
```

moy1_iem.cir
.MODEL MN NMOS LEVEL= MERCK2 EOX= 200E-10 MUO= 500

+ DPHIF= 0.8 DW= 1.0E-6 DL= 0.1E-6 VTO= 0.75
+ KB=0.6 REC= 0.1E-6 TG= 0.08 VL= 1.0E5 GL= 0.5E-6
+ KL= 0.3E-6 KW= 0.2E-6 DINF= 0.3 GW= 0.4E-6
+ LDIF= 3.5E-6 CDIFSO= 1.4E-4 CDIFPO= 8E-10
+ VE= 20E4 LMIN= 1.2E-6 WMIN= 3.4E-6 RSH= 500
mr vp vp r 0 mn w=200u l=2u
rr r 0 1k
m1 3 vp 1 0 mn w=200u l=2u
r1 1 0 1k
m2 4 vp 2 0 mn w=200u l=2u
r2 2 0 1.01k
m3 5 hb 3 0 mn w=200u l=2u
m4 6 hb 4 0 mn w=200u l=2u
m5 6 h 3 0 mn w=200u l=2u
m6 5 h 4 0 mn w=200u l=2u
m7 7 a 5 0 mn w=200u l=2u
m8 8 a 6 0 mn w=200u l=2u
r7 s1 7 1k
c7 7 0 10n
r8 s2 8 1k
c8 8 0 10n
* alims
vs1 s1 0 dc 10
vs2 s2 0 dc 10
va a 0 dc 7
ipol 0 vp 1m
.param d=2n
-param thold=490n+d
vh h 0 pulse( 3 4 10n 10n 10n thold 1u)
vhb hb 0 pulse( 4 3 10n 10n 10n thold 1u)
* simuls
.dc
.op
.tran 100n 100u
.defwave difis2=i(r7)-i(r8)
.plot tran i(r7) i(r8)
.plot tran w(difis2)
.width out=80
.option accusim2
.option iem
*.option newton eps=1.e-6
.option noascii
.extract average(w(difis2),98u,100u)
.end

```

\section*{Simulation Results}

Figure 16-4 compares the waveform produced by the Newton-Raphson method (shown in green) compared with the waveform produced by the IEM method (shown in yellow).

Figure 16-4. Example 4—moy1


\section*{Speed}

Speed gain ratio depends on the nature of the circuit simulated as well as the level of activity. Slowly varying circuits may manifest no gain. In the following circuits, a certain level of activity was present such as to show IEM advantage at default settings for both IEM and Newton-Raphson.

\section*{Example 5-ladder}

The speed-gain for IEM is about \(2.3 \times\) (as compared to Newton-Raphson).

\section*{Complete Netlist}

\section*{Note}

The netlist file is also provided as a Newton-Raphson version (ladder_nrm.cir) in the examples directory for comparison. The netlist is identical to ladder_iem.cir with the exception of . OPTION NEWTON selected for ladder_nrm.cir.
```

Simple R-Ladder Circuit
.param r=1K
.subckt r2r 1 2
R1 1 2 r
R2 2 0 {2*r}
D 0 2 DMOD OFF
.MODEL DMOD D CJO=1P
.ends r2r
*VIN 1 O pulse 0 1024 0 1n 1n 100U 1
vin 1 0 sin 1 1024 0.4g
x1 1 2 r2r
x2 2 3 r2r
x3 3 4 r2r
x4 4 5 r2r
x5 5 6 r2r
x6 6 7 r2r
x7 7 8 r2r
x8 8 9 r2r
R1 9 10 r
ROUT 10 0 r
.width out=80
.tran 0.1N 40N
.plot tran v(10)
.option accusim2
.option iem
*.option newton
.end

```

\section*{Simulation Results}

Figure 16-5 compares the waveform produced by the Newton-Raphson method (shown in green) compared with the waveform produced by the IEM method (shown in yellow).

Figure 16-5. Example 5—ladder


\section*{Example 6—opamp_5pin}

For this circuit, the speed-gain for IEM is about \(2.3 \times\) (as compared to Newton-Raphson).

\section*{Complete Netlist}

\section*{Note}
\(\qquad\)
The netlist file is also provided as a Newton-Raphson version (opamp_5pin_nrm.cir) in the examples directory for comparison. The netlist is identical to opamp_5pin_iem.cir with the exception of .OPTION NEWTON selected for opamp_5pin_nrm.cir.
```

opamp_5pin_iem.cir
.option TNOM=27
vIZ11 4 0 10V
VIZ9 0 5 10V
VDZO 6 0 SIN 0 1 1000 0 0
*.dc vdz0 1 -1 -0.01
*.plot dc v(3)
RIZ16 2 3 10K

```
```

RIZ14 6 1 10K
RIZ13 6 0 10K
RIZ12 0 2 10K
RIZ3 3 0 10K
XA1 2 1 3 4 5 LM107

* OPAMP MACROMODEL \$LM107
* NATIONAL LINEAR P3-140, 1982
* SUPPLY VOLTAGE(S): 15
* USAGE: XNAME <-> <+> <OUT> <VCC> <VEE> \$LM107
.SUBCKT LM107 2 3 6 7 4
V1 1004 0 1
DX1 0 1000 DMOD
DX2 0 1001 DMOD
DX3 1000 1002 DMOD
DX4 1001 1003 DMOD
VSINK 1002 1004 0
vSOURCE 1003 1004 0
FOUT 1000 1001 VO 1
FSOURCE 7 126 VSOURCE 1
FSINK 296 4 VSINK 1
IXX 6 0 0
VO 158 6 0
EVCC 126 5 7 5 1
EVEE 296 5 4 5 1
VLM2 5 115 55.7517
VLM1 116 5 55.7517
DD1 16 5 DD OFF
DD2 5 16 DD OFF
DCLP 158 112 DMOD OFF
DCLN 113 158 DMOD OFF
DLM1 106 116 DMOD OFF
DLM2 115 106 DMOD OFF
GDM 16 5 8 9 31.4165U
GCM 15 5 12 5 -21.2896M
GB 15 5 16 5 427.5729
JP 117 4 4 MMOD
EGND 5
ELIM 105 5 15 6 31.6228
VCHAIN 7 117 0
HCMR1 7 108 VCHAIN 222.535
HCMR2 110 4 VCHAIN 667.605
HCLP 126 112 VCHAIN 965.444
HCLN 113 296 VCHAIN 965.444
FEE 12 110 VCHAIN 1.4242M
FLIM 15 5 V40 1
V40 105 106 0
CE 12 5 1.25P
C1 8 9 2.5P
C2 15 16 5P
Q1 8 2 10 QM1
Q2 9 3 11 QM2
RE1 10 12 11.0128K
RC1 8 108 31.8304K
RE2 11 12 11.0128K
RC2 9 108 31.8304K
REE 12 5 1.0042G
*.opt abstol=1P vntol=1U reltol=1M
R2 5 16 0.1MEG

```
```

RO2 5 15 134
RO1 158 15 66
.MODEL QM1 NPN (IS=0.8F BF=40.6504)
.MODEL QM2 NPN (IS=0.8216F BF=42.735)
.MODEL DMOD D (N=1)
.MODEL DD D (N=30.1931)
.MODEL MMOD NJF (VTO=-0.6 BETA=4.993M)
.ENDS LM107

* BEGIN ELDO
.temp }2
.op
.TRAN 0.001 0.05 0
.plot tran v(3)
.plot tran v(6)
.width out=80
.option accusim2
.option iem
*.option newton
.end

```

\section*{Simulation Results}

Figure 16-6 compares the waveform produced by the Newton-Raphson method (shown in green) compared with the waveform produced by the IEM method (shown in yellow).

Figure 16-6. Example 6-opamp_5pin


Integral Equation Method (IEM) Speed

\section*{Chapter 17 Pole-Zero Post-Processor}

\section*{Introduction}

Eldo is able to obtain the locations of poles and zeros for analog circuits following a small signal analysis. This data is useful for obtaining stability and phase margin information as well as predicting closed loop performance from an open loop response. As a lot of closely spaced poles or zeros are not easily discernible via a Bode plot, the interactive post processor and its textual output clearly help to identify such singularities and evaluate the most important areas in a circuit's behavior.

The pole-zero data is obtained by linearizing the circuit about an operating point and outputting information about circuit matrix description and AC response. This data will be analyzed by the Eigenvalue QZ algorithm, one of the most accurate techniques available.

The pole-zero post-processor allows the designer to detect all the roots of the analyzed circuit and to simplify this information extracting the most meaningful of these roots. Moreover, a high level model of the reduced circuit-equivalent for AC and small signal analysis-is calculated and given in the form of an FNS device which can replace the original circuit when used as part of a more complex design.

The pole-zero post-processor may be activated for circuits which have been simulated using the . \(\mathbf{P Z}\) and . AC commands. The . Pz command can take either the voltage at a node, between two nodes or the current through a voltage source as parameters. The pole-zero analysis determines the transfer function relationship-expressed as complex poles and zeros-between the input where the AC voltage source is applied and the output specified as a parameter in the \({ }_{.} \mathbf{P z}\) command.

Pole-zero only works on quasi-static devices; pole-zero would give incorrect results on HDL-A models which are not linear with OMEGA ( \(\exp (\mathrm{OMEGA})\) for instance). However, for HDL-A models that make use of derivatives of order higher than 2 it is possible to declare additional IMPLICIT states and make the model linear in OMEGA.

\section*{Example}

In 'pseudo' HDL-Av1 code, convert:
\[
\begin{aligned}
b & =d d t(a) \\
c & =d d t(b) ;
\end{aligned}
\]
into:
```

EQUATION (b,c) FOR ac,dc,transient =>
b == ddt(a);
c == ddt (b);

```

\section*{Running the Dialog for Pole-Zero Analysis}

Before running the pole-zero post-processor, you must make sure that an AC analysis has been performed on the circuit of interest and that a .PZ command has been included in the netlist. This has the effect of producing a file called <circuit>.pz in the output directory.

The pole-zero post-processor can be run in batch mode or interactive mode:
- Batch mode, run:
```

pz <circuit>.pz -batch

```

The pole-zero post-processor will run until completion using default answers to questions usually prompted by the tool
- Interactive mode, run:
pz <circuit>.pz
In this mode, you type in answers to all questions prompted by the tool. The arguments to provide are the following:
-th value
threshold for pole/zero cancellation
```

-cutoff value

```
cutoff frequency
```

-pindices indice_list -endpindices

```
list of indexes for pole selection; indices must be in increasing order
```

-zindices indice_list -endzindices

```
list of indexes for zero selection; indices must be in increasing order
Note that if one of the arguments is provided, then answers to those pz questions which do not have explicit answers in the argument list will take the default answer, that is, the same as for the -batch mode.

The first result is the impression of all the roots found for the circuit, ordered by magnitude but with zeros divided in negative and positive real parts, as follows for a typical example:
\begin{tabular}{lllr} 
Poles & Modulus & Real Part & Imaginary Part \\
1 & \(6.264953 \mathrm{E}+00\) & \(-6.264953 \mathrm{E}+00\) & \(0.000000 \mathrm{E}+00\) \\
2 & \(3.853866 \mathrm{E}+06\) & \(-3.824006 \mathrm{E}+06\) & \(-4.788095 \mathrm{E}+05\) \\
3 & \(3.853866 \mathrm{E}+06\) & \(-3.824006 \mathrm{E}+06\) & \(4.788095 \mathrm{E}+05\) \\
4 & \(4.396770 \mathrm{E}+06\) & \(-4.396770 \mathrm{E}+06\) & \(0.000000 \mathrm{E}+00\) \\
5 & \(5.423444 \mathrm{E}+06\) & \(-5.423444 \mathrm{E}+06\) & \(0.000000 \mathrm{E}+00\) \\
6 & \(6.554762 \mathrm{E}+06\) & \(-3.126871 \mathrm{E}+06\) & \(-5.760866 \mathrm{E}+06\) \\
7 & \(6.554762 \mathrm{E}+06\) & \(-3.126871 \mathrm{E}+06\) & \(5.760866 \mathrm{E}+06\) \\
8 & \(6.584083 \mathrm{E}+06\) & \(-5.150248 \mathrm{E}+06\) & \(-4.101840 \mathrm{E}+06\)
\end{tabular}
\begin{tabular}{lrrr}
9 & \(6.584083 \mathrm{E}+06\) & \(-5.150248 \mathrm{E}+06\) & \(4.101840 \mathrm{E}+06\) \\
10 & \(1.343013 \mathrm{E}+07\) & \(-1.343013 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
11 & \(1.531050 \mathrm{E}+07\) & \(-1.531050 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
12 & \(2.217833 \mathrm{E}+07\) & \(-2.217833 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
13 & \(4.927351 \mathrm{E}+07\) & \(-4.927351 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
14 & \(6.564085 \mathrm{E}+07\) & \(-6.564085 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
15 & \(1.228260 \mathrm{E}+08\) & \(-1.228260 \mathrm{E}+08\) & \(0.000000 \mathrm{E}+00\) \\
Zeros & Modulus & RealPart & Imaginary Part \\
1 & \(3.853866 \mathrm{E}+06\) & \(-3.824006 \mathrm{E}+06\) & \(-4.788095 \mathrm{E}+05\) \\
2 & \(3.853866 \mathrm{E}+06\) & \(-3.824006 \mathrm{E}+06\) & \(4.788095 \mathrm{E}+05\) \\
3 & \(4.396770 \mathrm{E}+06\) & \(-4.396770 \mathrm{E}+06\) & \(0.000000 \mathrm{E}+00\) \\
4 & \(5.423444 \mathrm{E}+06\) & \(-5.423444 \mathrm{E}+06\) & \(0.000000 \mathrm{E}+00\) \\
5 & \(6.435558 \mathrm{E}+06\) & \(-5.867538 \mathrm{E}+06\) & \(-2.643560 \mathrm{E}+06\) \\
6 & \(6.435558 \mathrm{E}+06\) & \(-5.867538 \mathrm{E}+06\) & \(2.643560 \mathrm{E}+06\) \\
7 & \(6.554762 \mathrm{E}+06\) & \(-3.126871 \mathrm{E}+06\) & \(-5.760866 \mathrm{E}+06\) \\
8 & \(6.554762 \mathrm{E}+06\) & \(-3.126871 \mathrm{E}+06\) & \(5.760866 \mathrm{E}+06\) \\
9 & \(1.343013 \mathrm{E}+07\) & \(-1.343013 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
10 & \(1.531050 \mathrm{E}+07\) & \(-1.531050 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
11 & \(2.217833 \mathrm{E}+07\) & \(-2.217833 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
12 & \(6.564085 \mathrm{E}+07\) & \(-6.564085 \mathrm{E}+07\) & \(0.000000 \mathrm{E}+00\) \\
13 & \(1.228260 \mathrm{E}+08\) & \(-1.228260 \mathrm{E}+08\) & \(0.000000 \mathrm{E}+00\) \\
14 & \(3.857487 \mathrm{E}+06\) & \(3.857487 \mathrm{E}+06\) & \(0.000000 \mathrm{E}+00\) \\
15 & \(2.908742 \mathrm{E}+09\) & \(2.908742 \mathrm{E}+09\) & \(0.000000 \mathrm{E}+00\)
\end{tabular}

At this point it is possible to simplify the results, since in practice many poles and zeros will be output and some of them will be almost superimposed giving a negligible resultant effect.
Moreover, sometimes the circuit will work in a well determined frequency range over which we will focus our attention, while also all the parasitic and less meaningful roots will be detected. That is why the following reduction mechanisms are available.

\section*{Frequency Limit}

The program asks the user if he wants to limit the analysis up to a certain frequency. Here is such a dialog:
```

Do you want to set an upper frequency limit for the selected poles and
zeros? [yes/no]:
Y
So give the highest frequency to be considered:
5e7
Roots up to 0.5000E+08 Hz will be examined.

```

If the roots of your circuit are spanned up to a frequency quite a lot higher than the upper frequency of your AC analysis, this limit can be very useful in simplifying textual output and FNS models without meaningful loss of accuracy.

\section*{Pole-Zero Cancellation by Threshold}

Very close poles and zeros can be deleted as their influence on the circuit behavior compensates. Big circuits with a lot of roots often have closely spaced poles and zeros which can be deleted to show the most meaningful remaining roots. A prompt reminds the user about
the threshold mechanism, showing the condition to delete a pole \(\mathbf{P}\) and a zero \(\mathbf{Z}\). The condition is that:
```

abs(RE[P]-RE[Z]) < abs(RE[P]) \diamond TH + TH

```
and the same for the imaginary part.
Therefore, if a threshold of say, 0.1 is given, there are two possibilities:
- For very low frequency roots, say fractions of 1 Hz, тн has the meaning of maximum difference between the real parts of the pole and the zero, and the same for the imaginary part.
- In most cases, there are roots at quite high frequencies so the first term on the right side of the relation dominates and TH takes the meaning of maximum ratio between the distance amongst the roots and their value, so in this case a \(10 \%\) tolerance.

At this point, a table of remaining poles and zeros (after the two elimination steps) is given.

\section*{Hand Selection}

After these steps, the user can still express a further choice between the resulting roots. A prompt asks:
```

Do you agree with the Selected POLES [Yes/No]?

```

If the selected poles and zeros are Ok , then press Y and the analysis goes on. If only a certain number of poles and zeros are required, press N to reveal the following prompt:
```

Poles selection by their index in INCREASING order

```

Enter a negative index to end the selection.

\section*{Select Index}

The user is asked to select which poles are to be included in the final transfer function. The selection is made via the index to the values-the index being the first number which appears in the tables above. Once the values to use have been chosen, the selection is terminated by entering a negative number. The same dialog then starts for zeros.

\section*{Note}

Make sure the selections are made in increasing integer order including the negative terminator otherwise required values may be lost.

The remaining set of poles and zeros are printed, followed by another table showing the difference between the actual and the now approximated model, swept in frequency and giving both the magnitude ( dB ) and the phase (degree) differences. This is shown below:
\begin{tabular}{lll}
Hz & \(\mathrm{dB}^{\prime} \mathrm{s}\) Error & Degrees Error \\
\(1.000000 \mathrm{E}+01\) & \(6.525140 \mathrm{E}-04\) & \(1.020462 \mathrm{E}-02\) \\
\(1.000000 \mathrm{E}+02\) & \(6.201058 \mathrm{E}-04\) & \(1.096881 \mathrm{E}-02\) \\
\(1.000000 \mathrm{E}+03\) & \(5.805557 \mathrm{E}-04\) & \(1.102087 \mathrm{E}-02\) \\
\(1.000000 \mathrm{E}+04\) & \(5.806112 \mathrm{E}-04\) & \(1.107192 \mathrm{E}-02\) \\
\(1.000000 \mathrm{E}+05\) & \(5.791327 \mathrm{E}-04\) & \(3.599889 \mathrm{E}+02\) \\
\(1.000000 \mathrm{E}+06\) & \(5.815470 \mathrm{E}-04\) & \(1.444244 \mathrm{E}-02\) \\
\(1.000000 \mathrm{E}+07\) & \(1.179731 \mathrm{E}-03\) & \(4.588650 \mathrm{E}-02\) \\
\(1.000000 \mathrm{E}+08\) & \(5.953287 \mathrm{E}-02\) & \(3.609858 \mathrm{E}-01\) \\
\(1.000000 \mathrm{E}+09\) & \(4.490041 \mathrm{E}+00\) & \(2.134625 \mathrm{E}+00\)
\end{tabular}

\section*{FNS Model}

The reduced circuit is now modeled as an S-domain transfer function (say an FNS device in Eldo syntax) which can replace the original circuit with the introduced approximations for AC and small signal analysis-this can be very useful for developing complex designs, allowing the replacement of even a complex block with its equivalent model and great simplification of simulation of the higher level system. The output format is shown below:
```

FNS1 IN OUT
+

+ 498057.650621
+ 0.0271151244556 ! * s^ (-1)
+ 4.88425501019e-10 ! * s^(-2)
+ 2.65330374224e-18 ! * s^(-3)
+ -3.22583377778e-27 ! * s^ (-4)
+ 8.84119411e-37 ! * s^(-5)
+ ,
+ 1
+ 0.0315272851854 ! * s^(-1)
+ 1.08957721435e-09 ! * s^(-2)
+ 1.85561098689e-17 ! * s^(-3)
+ 2.03791858143e-25 ! * s^(-4)
+ 1.03556420914e-33 ! * s^(-5)

```

If too many poles and zeros are left after the reduction steps, FNS evaluation could fail due to too high coefficients (a message is printed in such a case). However, the efficiency of the reduction algorithm normally allows a reduction of at most 6-7 poles which can give a very good approximation of the original circuit.

The PZ program produces a <circuit>.cpz output file to be visualized with EZwave which shows the Bode diagrams of gain and phase for the original and the reduced circuit. Also, a file <circuit>.mpz is written, showing a scatter map of the circuits roots in the complex plane. And finally, a subcircuit containing FNS is stored in file <circuit>.pzck, which can be included by an upper level netlist.

After all these steps, the user is asked whether they wish to repeat the analysis, typically to alter some parameters such as threshold, frequency limit, and so on, thereby modifying the accuracy/simplicity ratio of the whole analysis.

When "no" is the answer, the program is exited leaving an ASCII output file <circuit>.pzr containing a trace of all the program outputs and the dialog.

\section*{Pole-Zero Numerical Issues}

There are possible numerical issues with poles and zeros. This section explains why 500 variables is a reasonable maximal system size, and suggests a workaround using a two-step S-parameter block approach.

The .PZ command generates \(G\) and \(C\) matrices. The pole-zero post-processor computes poles and zeros, and generates approximated FNS to be used. It uses a QZ algorithm to solve the generalized Eigenvalue system:
\[
\mathrm{GX}=\lambda \mathrm{CX}
\]

The CPU cost of the QZ algorithm is approximately \(n^{3}\), where \(n\) is the size of the \(G\) and C matrices. When \(n>500\), the CPU time is large, and numerical issues may arise. This is a constraint of the QZ algorithm.

Workaround: Use a two-step S-parameter block approach:
1. Extract the S-parameters of the circuit (using .FFile and .Ac commands)

This generates a.\(s 2 p\) file containing the \(S\)-parameters.
2. Use this S-parameter file in either of these ways:
- Use this S-parameter file (. \(s 2 p\) ) as a macromodel of the circuit (using an FBLOCK model)

This is more accurate than the FNS pole-zero approach.
- Alternatively, specify the . PZ command with the S-parameter file (. \(s 2 p\) ) (using an FBLOCK model)

The pole-zero post-processor can then be used to compute the poles and zeros as before, avoiding any numerical issues.

\title{
Chapter 18 Optimizer in Eldo
}

\section*{Introduction}

\section*{Overview}

The Eldo optimizer is a general-purpose electrical circuit optimization program. The optimizer will calculate the value of parameters (the optimization variables) in the circuit such that the behavior or the characteristics of the circuit conform as close as possible to the specifications. The optimizer can achieve a simultaneous improvement in AC, DC, Transient domain, Steady-State and Modulated Steady-State analyses.

The designer specifies the design objectives and the optimizer will adjust the component parameters of the circuit (such as resistor or capacitor values, the \(\beta\) value of a transistor, widths and lengths of a MOSFET) in order to meet a specified electrical performance. Optimization can be applied to:
- Circuit parameters
- Model parameters
- Element parameters
- Device lengths, widths, areas, and peripheries.

The parameter values must conform to the manufacturing limits, process limits, or discrete device values. To achieve this, restrictions can be specified on the design parameters. Various constraints (or inter-relations) can be specified, for example, circuit parameters must be non-negative, or must not violate upper boundaries. In addition, more complicated constraints can be specified, for example, how components physically interact with each other to produce non-linear relations.

The process of identifying the objective, variables, and constraints for a specific problem is known as modeling. The construction of an appropriate model is the first step (sometimes the most important) in the optimization process. If the model is too simplistic, it will not generate useful insights into the practical problems. If too complex, it may become difficult to solve. Thus, the designer's task is to discover what is the most appropriate model for their requirements for more information please refer to "Modeling Capabilities in Eldo and Optimization" on page 1165.

The term Eldo optimizer refers to the complete set of optimization tools available through the . Optimize command. In some circumstances it is necessary to be more precise about the underlying method or algorithm, therefore the nomenclature in Table 18-1 will be used.

\section*{Table 18-1. Nomenclature}
\begin{tabular}{lll} 
Name & Algorithm/Method & Command \\
\hline Eldo optimizer/Passfail & Pass or fail technique & .OPTIMIZE METHOD=PASSFAIL \\
Eldo optimizer/Bisection & \begin{tabular}{l} 
Dichotomy (or bisection) \\
algorithm
\end{tabular} & .OPTIMIZE METHOD=BISECTION
\end{tabular}

This documentation is mainly dedicated to the Eldo optimizer/SQP. The other group of methods (Bisection, Secant and Passfail) represent a specific class of algorithms pertaining to the category of Derivative Free Optimization (DFO) algorithms. They allow optimization in the restricted case of one dimensional problems. These methods will be documented as special cases of the default algorithm.

\section*{Problem Statement}

In order to use the Eldo optimizer, the designer must provide the following information:
- The nominal circuit, identical to the circuit provided for simulation in the netlist format. The user must have a working netlist.
- The design variables, the designer must specify those parameters that may be optimized by the optimizer in its search for an optimal solution. The designer's selection of variables is accomplished by making minor modifications to the working netlist, using the .PARAMOPT command. Please refer to ".PARAMOPT" on page 1142.
- The design objectives may be any quantity represented by a real value, a combination of quantities that are generated by multiple sweep commands, or multiple increment step on circuit parameters. For example, a profile describing the frequency response desired for a filter circuit. Eldo provides a number of methods for specifying a waveform to match, or by simply defining point(s) that correspond to the desired behavior. These design objectives are specified by adding data and simple arguments to the . obлective command (or the .EXTRACT and .meas commands). This important point is explained in "Modeling Capabilities in Eldo and Optimization" on page 1165.

The information that the user has to provide is referred to as the problem statement. The designer provides a model for the optimization problem, this may be the minimization or maximization of functions (extracted measures) subject to the constraints on its variable.

For example, the . PARAMOPт command is used to specify the length 1 and the width \(w\) of a MOS transistor:
```

.PARAMOPT

+ L=(10U, 2U, 100U)
+W=(60U, 2U, 200U)

```

These commands can be expressed mathematically as the inequalities:
\[
2 \times 10^{-6} \leq 1 \leq 10^{-4}
\]
and
\[
2 \times 10^{-6} \leq w \leq 2 \times 10^{-4}
\]

The first value given in the command .PARAMOPT \(\mathbf{L}=(10 \mathrm{U}, 2 \mathrm{U}, 100 \mathrm{U})\) is used to initialize the optimization algorithm.

On the other hand, the objective function will be specified by adding a . obsective command. For example, the optimization of the phase margin for an operational amplifier in closed-loop configuration:
```

.OBJECTIVE AC

+ LABEL=phasemarg ( XYCOND(VP (out),VDB(out) < 0) + 180 )
+ LBOUND=50.0

```

Once the design parameters and the design objective have been defined, the user must add the . optimize command to the netlist file, and execute Eldo.

\section*{Invoking the Eldo Optimizer}

The Eldo optimizer can be invoked from the command line in the same way as Eldo:
```

eldo <circuit_name> <other_arguments>

```

\section*{Exploiting the Results of Optimization}

After the optimization algorithm has been applied, the designer must be able to recognize whether it has succeeded in its task of finding a solution. This can be accomplished by analyzing the results of the optimization.
- There are the final diagnostics for checking that the current set of variables is a solution of the problem. If the optimal conditions are not satisfied, they may give useful information on how the current estimate of the solution can be improved. Users may think of this as a global score of the optimization run.
- There are also the values of the extracted measures printed during the optimization our at the end of the process. This represents the post-optimization analysis.

The designer will find this kind of information within the output results of Eldo (.chi file) and the Eldo optimizer (.otm file). The script viewotm can be invoked to extract the desired results. This script can be invoked from the command line as follows:
```

viewotm -f <circuit_name>.otm <other_arguments>

```

Please refer to "Exploiting Output Results" on page 1190 for more information.
From the optimizer's point of view, it is important to understand that the only way to check optimality (or success) is to compute some measure of optimality and feasibility at the final solution. There is no other criterion (the optimizer is not an expert in circuit design). If this optimality measure is less than some specified tolerance, the current point is considered as optimal. The fundamental notions of optimality and feasibility are considered in a semi-rigorous way along this documentation, for more information please refer to "Role of tolerances in Eldo optimizer/SQP" on page 1186. These ideas are presented as concise as possible, but it is not mandatory if the user wishes to avoid technical details.

\section*{Optimization Commands}

The following are commands that can be used for optimization:
- .EXTRACT and .MEAS
- .OBJECTIVE
- .OPTIMIZE
- .PARAMOPT

In the descriptions, we will use the tokens iVALUE and RVALUE to denote integer and real (or floating) numbers.

\section*{.EXTRACT and .MEAS}

In the context of optimization, this command is an extension of the .EXTRACT command. The additional arguments (GOAL, equal, lbound, ubound, and weight) have no effect when the .optimize is not specified in the netlist. The documentation of the .extract command defines two categories of design objectives:
- those represented by a single number (scalar version)
- the objectives represented by a vector of measures.

These two categories are described in the following sections with some known limitations.

\section*{Command Syntax for Scalar Objectives}

The general specification can be written as:
```

. EXTRACT

+ [EXTRACT_INFO] [LABEL=NAME] [FILE=FNAME]
+ [VECT] [CATVECT] \$MACRO|FUNCTION
+ [OBJECTIVE_INFO]

```

\section*{Parameters}
- [EXTRACT_INFO] [LABEL=NAME] [FILE=FILE_NAME] [VECT] [CATVECT]

Please refer to ".EXTRACT" on page 637 for more information.
- \$MACRO| FUNCTION

Instantiation of a macro (preceded by the ' \(\$\) ' character), or an expression that uses the Extraction Language of Eldo.
- OBJECTIVE_INFO:=

GOAL=MINIMIZE|MAXIMIZE [WEIGHT=RVALUE]
GOAL=RVALUE [WEIGHT=RVALUE]
EQUAL=RVALUE
| \{LBOUND=RVALUE | UBOUND=RVALUE \}
| LBOUND=RVALUE UBOUND=RVALUE
The objective_Info argument describes the category of the design objective when optimization is required. When this argument defines a minimize or maximize objective, the specified expression will be minimized or maximized. The argument GOAL=RVALUE defines a soft constraint on the measure, while the lbound, ubound and equal define hard constraints. The specification of the arguments GOAL, EQUAL, LBOUND, and/or UBOUND is mandatory for optimization. The default value of GOAL when none is defined is 0 ; this does not apply to the passfail method. The weight argument is a positive value attached to the design objective. The weight can be thought of as quantifying the user's desire to make the objective important or not.

\section*{Command Syntax for Vector Objectives}

The specification of vector objectives is performed with the .EXTRACT FITTING command.
```

.EXTRACT

+ [EXTRACT_INFO] [IABEL=NAME] [FILE=FILE_NAME ]
+ [VECT] [CATVECT]
+ FITTING
+ TARGET_NAME \$MACRO|FUNCTION
+ [SCALE_INFO] [WEIGHT=RVALUE]
+ [INTERP_INFO | SELECT_INFO]

```

\section*{Parameters}
- [EXTRACT_INFO] [LABEL=NAME] [FILE=FILE_NAME] [VECT] [CATVECT]

Please refer to ".EXTRACT" on page 637 for more information.
- TARGET_NAME

Name of the discretized curve to fit. It can be the name of a previously defined wave or the reference to a variable in a .DATA statement (for more information run the example fourband in the directory: \$MGC_AMS_HOME/examples/optimizer).
- \$MACRO|FUNCTION

Instantiation of a macro (preceded by the '\$' character), or an expression that uses the Extraction Language of Eldo.
- SCALE_INFO: = [LINEAR|LOG|LOG10]

The LINEAR, LOG, and LOG10 select the scale of the x -axis for the extracted measures.
- INTERP_INFO:= INCR=RVALUE

The INTERP_INFO argument is meaningful only when goal values are specified through .DATA statements. The INCR value will be the step in the analysis sweep variable to be used for generating goal values by a piece wise linear interpolation of data provided by an associated .DATA command.
- SELECT_INFO:= DEC=RVALUE

The DEC argument is the number of points per decade in the analysis sweep variable to be used for generating goal values using a logarithmic interpolation of the provided data points. The corresponding simulated values are obtained by interpolation of the available simulated values.

\section*{Notes}
- The user can specify a multi-dimensional specification of goal objectives, this is equivalent to specifying the .EXTRACT FITting command.
- Coherency has been enforced between analysis commands and objective specifications. The following example is representative. Some dC operating point analyses are performed for every value of VDS from 0 to 40 with a step increment of 1 , and every value of vgs between 4 and 16 with a step increment of 2 . Three design objectives are defined for the variable IDS through the .DATA labeled MOSFIT, corresponding to the values of VGS equal to 4 and the values of VDS equal to 1,2 , and 3 respectively. The current at node VDRAIN is optimized to fit the values of IDS. The values of VDS and

VGS for the measurements correspond to the simulation points on a short range as specified in the .DC command.
```

.DC VDS 0 40 1 VGS 4 16 2
.EXTRACT DC LABEL=FIT_IDS

+ FITTING
+ MOSFIT(IDS) I(VDRAIN)
.DATA MOSFIT
+ VDS VGS IDS
+1.000E+00 4.000E+00 1.574E+00
+2.000E+00 4.000E+00 1.806E+00
+ 3.000E+00 4.000E+00 1.826E+00
.ENDDATA

```

Such situation is now detected and forbidden. In this case, the analysis command should be driven by the values of VDS and VGS specified in the .DAta. The use of .DATA constructs is then restricted.

Consider the next example. A small signal analysis is performed for frequencies in the range [ \(100 \mathrm{kHz}, 1 \mathrm{GHz}\) ] with 2 points per decade. The voltage magnitude at node 16 is optimized to fit the values of the data labelled V16 in the statement .DAtA Vm16.
```

.AC DEC 2 100k 1g
.EXTRACT AC LABEL=FIT_VM16

+ FITTING
+ VFIT(V16) VM(16)
.DATA VFIT
+ FREQ V16
+ 100K 200
+ 30Meg 200
+ 1G 1m
.ENDDATA

```

There are three measurement points defined at \(100 \mathrm{kHz}, 30 \mathrm{MHz}\) and 1 GHz respectively. In the former version of Eldo (v6.6), the values of \(\mathrm{vm}(16)\) at these frequencies were obtained by interpolation of the values simulated according to the . AC analysis command. Interpolation for measures is now forbidden with optimization, since this technique introduces additional errors that cannot be bounded, and gives nonsmooth measurements. When optimization is required the simulation points must be included in the set of simulation points.

\section*{.OBJECTIVE}

\section*{.OBJECTIVE}

The . objective command is based on the extract construct, and specifically dedicated to optimization. Some restrictions are imposed and the semantic is different in some situations. The specification of design objectives has been simplified. The following is a list of reasons of using the .obJective command:
- Some implicit rules in the extract construct are not well fitted for optimization. For example, when several ALter blocks are used with optimization, the .EXTRACT commands are simply added to each ALTER blocks. The notion of scope related to a .EXTRACT command was not clearly defined. By default, the . obJective commands have a local scope.
- It is easier to separate the optimization block, the circuit statements, and the plot statements.
- In the .chi file, it is difficult to print the values of objectives as they are effectively processed in the optimizer.
- The dump of the results into a file (using the file argument) is not of great use. Moreover, vector optimization makes the results difficult to read.
- The actual version of this command is limited to the basic analyses such as DC, TRAN, and AC. This list will be completed in the subsequent releases of the optimizer.

\section*{Note}

For backward compatibility, the equivalent of the . ObJECTIVE command can be specified with the .EXtract command.

\section*{Command Syntax}

The general specification can be written as:
```

.OBJECTIVE

+ EXTRACT_INFO [LABEL=NAME]
+ {\$MACRO|FUNCTION}
+ OBJECTIVE_INFO
+ [SCALING_INFO]
+ [PRINT_INFO]

```

\section*{Parameters}
- [EXTRACT_INFO] [LABEL=NAME]

The argument EXTRACT_INFO must be replaced by one element of the following list of analyses: dC, DCTRAN, tran, dCAc, or ac. An analysis can be omitted, in this case the argument \$MACRO|FUNCTION must represent a valid expression that refers to other extracted measures.

\section*{- \(\quad\) SMACRO \(\mid\) FUNCTION}

Instantiation of a macro (preceded by a ' \(\$\) ' character), or expression that uses the Extraction Language of Eldo.
- OBJECTIVE_INFO:=

GOAL=MINIMIZE|MAXIMIZE [WEIGHT=RVALUE]
| GOAL=RVALUE [WEIGHT=RVALUE]
| EQUAL=RVALUE
| \{Lbound=RVALUE | UBOUND=RVALUE\}
| LBOUND=RVALUE UBOUND=RVALUE
The obJective_info argument describes the category of the design objective when optimization is required. When this argument defines a minimize or maximize objective, the specified expression will be minimized or maximized. The argument GOAL=RVALUE defines a soft constraint on the measure, while the lbound, ubound and equal define hard constraints (see "Notes" on page 1136 for the definition of hard and soft constraints) The specification of the arguments GOAL, EQUAL, LBOUND, and/or UBOUND is mandatory for optimization. The weight argument is a positive value attached to the design objective. The weight can be thought of as quantifying the user's desire to make the objective important or not.
- SCALING_INFO:= TYPVAL=RVALUE

This argument allows the user to specify the typical value or the scale factor associated to the objective. Please refer to "Scaling of variables and objectives" on page 1177 for more information.
- MONITOR_INFO:= MONIT_VAL [=QUALIFIER \{, QUALIFIER\}]]
where QUALIFIER=MAX \(\mid\) MIN \(\mid\) MEAN \(\mid\) ERRMAX \(\mid\) ERRMIN \(\mid\) ERRMEAN
max The maximum value of the multi-point objectives. Optional.
min The minimum value of the multi-point objectives. Optional.
mean The mean value of the multi-point objectives. Optional.
errmax The maximum value of the error functions for the multi-point objectives. Optional.
errmin The minimum value of the error functions for the multi-point objectives. Optional.
errmean The mean value of the error functions for the multi-point objectives. Optional.
The monit_val argument allows the user to specify how the current values of a design objective are printed during optimization. This option affects only the .otm file (the Eldo optimizer output) but not the .chi file or the standard output. It is possible to have multiple options, they should be separated by commas, for example: mONIT_VAL=MAX, ERRMAX... Default value is mean. See "How to monitor the design objectives (MONIT_VAL options)" on page 1195 for the details.
- PRINT_INFO:= PRN_VAL=\{NO|YES \(\}\)

The prn_val argument allows the user to specify whether the values of a specific objective must be printed. By default PRN_VAL=YES, all the components of a design objective are printed.

\section*{Notes}
- The additional data such as the goal values, the lower/upper bounds, and the weight numbers are sent to the optimizer when initializing the optimization process. They have constant values during the whole process.
- Excepting the design objectives specified with GOAL=minimize|maximize, which play a specific role in the problem statement, the goal values and the bounds have multi-point extension. This feature is related to data driven analysis. For an example please refer to "Effect of multiple sweeps and step increments" on page 1182.
- Note that some of the arguments in objective_info are mutually exclusive. For instance, an objective cannot be specified at the same time as an equality and as an inequality. The user may think of as an extracted measure having a unique descriptor that gives its role within the problem.

These rules are restrictive. From a mathematical viewpoint, it makes sense to minimize and bound a design objective, or to specify a goal value and a range of values for an objective. This must be done on separate commands.
- In general not all equality and inequality constraints are perceived by designers in the same way. It leads to classify constraints as either hard or soft.
The term hard constraints means refers to the constraints the designer considers as most essential, i.e. they have to be satisfied. The designer does not want them to take part in any subsequent design trade-off. For example, any constraint required for physical reliability must be treated as a hard constraint.
In contrast, soft constraints are those that the designer is interested in trading off against one another and against the performance objectives during intermediate iterations of an optimization run. Note that minimize and maximize objectives are naturally candidates for trade-off.
- The Eldo optimizer/SQP method is the only algorithm supporting the complete set of arguments in objective_info. For example, the statement:
```

.OBJECTIVE {...} GOAL=MINIMIZE|MAXIMIZE

```
have no sense when used with the Dichotomy and Secant methods. These methods are only dedicated to solve equations of the form \(\mathrm{F}(\mathrm{x})=0\). An error message will be raised in these cases.

These restrictions are described in Table 18-2:
Table 18-2. .OBJECTIVE Restrictions
\begin{tabular}{|c|c|c|c|c|c|c|}
\hline Statement & Notation & Goal Value & \begin{tabular}{l}
Lower \\
Value
\end{tabular} & \begin{tabular}{l}
Upper \\
Value
\end{tabular} & Weight Value & Supported Methods \\
\hline \[
\begin{aligned}
& \text {.OBJECTIVE \{...\} } \\
& +\quad \text { GOAL=MINIMIZE }
\end{aligned}
\] & \(\mathrm{f}_{\mathrm{m}}(\mathrm{x})\) & N/A & N/A & N/A & \(\mu_{\mathrm{m}}\) & SQP, Search \\
\hline \[
\begin{aligned}
& \hline \text {. OBJECTIVE }\{\ldots\}\} \\
& +\quad \text { GOAL=MAXIMIZE }
\end{aligned}
\] & \(-\mathrm{f}_{\mathrm{m}}(\mathrm{x})\) & N/A & N/A & N/A & \(\mu_{\mathrm{m}}\) & SQP, Search \\
\hline \[
\begin{aligned}
& \text {. OBJECTIVE }\{\ldots\} \\
& + \text { GOAL=r }
\end{aligned}
\] & \(\mathrm{f}_{\mathrm{r}}(\mathrm{x})\) & r & N/A & N/A & \(\mu_{\mathrm{r}}\) & SQP, Search, Secant, Dichotomy \\
\hline \[
\begin{aligned}
& \text {. OBJECTIVE }\{\ldots\} \\
& + \text { EQUAL=e }
\end{aligned}
\] & \(\mathrm{f}_{\mathrm{e}}(\mathrm{x})\) & e & N/A & N/A & Not used & SQP, Search, Secant, Dichotomy \\
\hline \[
\begin{aligned}
& \text {. OBJECTIVE }\{\ldots\} \\
& + \text { LBOUND }=1 \\
& + \text { UBOUND }=u
\end{aligned}
\] & \(\mathrm{f}_{\mathrm{i}}(\mathrm{x})\) & N/A & 1 & u & Not used & SQP \\
\hline
\end{tabular}

\section*{.OPTIMIZE}

This section is concerned with the optimization command acting on the behavior of the Eldo optimizer algorithms. In some specific cases, designers can perform optimization using the DICHOTOMY, the SECANT and PASSFAIL methods. Eldo can run the optimizer without using the default algorithm Eldo optimizer/SQP. This can be applied when there is only one goal (specified through a GOAL=RVALUE statement) and one parameter to optimize. Note that the . OPtimize command is compatible with the multiple run features (see the command description for ".MPRUN" on page 729).

\section*{Command Syntax}

The optimization specification acting on all the analyses specified in the circuit netlist is done using the following command:
```

.OPTIMIZE

+ [METHOD=DICHOTOMY |SECANT |PASSFAIL|SEARCH]
+ [QUALIFIER=VALUE {, QUALIFIER=VALUE}]
+ [PARAM=LIST_OF_VARIABLES|*]
+ [RESULTS=LIST_OF_MEASURES|*]
+ [OUTER=LIST_OF_PARAMETERS]

```

\section*{Parameters}
- qualifier

The name of the corresponding configuration argument (see Eldo Optimizer/SQP Arguments).
- PARAM=LIST_OF_VARIABLES

List of comma-separated variables to be tuned, specified with the .PARAMOPT command.
- RESULTS=LIST_OF_MEASURES

List of comma-separated measures to be optimized, specified with .EXTRACT and/or .MEAS commands.
- OUTER=LIST_OF_PARAMETERS

List of comma-separated design parameters specified with the .PARAM command and used in a .STEP PARAM command. For more information, please refer to "Outer and inner design parameters" on page 1170.

Note
If the specification of design variables with PARAM= is omitted or if the character * is specified in place of an explicit list, all the variables specified by a .PARAMOPT command are optimized. If the specification of objectives with results \(=\) is omitted or if \(*\) is specified in place of an explicit list, then all the design objectives specified by a . ObJECTIVE (or a .EXTRACT/.meas command) are optimized.

\section*{Eldo Optimizer/SQP Arguments}

The performance of the solver (the SQP algorithm) is controlled by a number of parameters. Each option has a default value that should be appropriate for most problems. The defaults are given below. For specific situations it is possible to specify non-standard values for some or all of the parameters. If experimentation is necessary, it is recommend that the user only changes one option at a time.
- MAX_ITER=IVALUE

Maximum number of iterations permitted for optimization. Default 1000.
- MAX_SIMUL=IVALUE

Maximum number of circuit simulations allowed. Default 99999.
- TOL_OPT=RVALUE

Tolerance on optimality conditions. This parameter specifies the accuracy to which the user wishes the final iterate to approximate a solution of the problem. тод_Opt can be considered as indicating the level of accuracy (i.e. the number of significant figures) desired in the design functions at the solution. Specifying only the value тOL_OPT has the same effect as setting separately both the tolerances TOL_GRAD=TOL_OPT and TOL_FEAS \(=10^{-2} \times\) тоц_OPт. Default value is \(10^{-4}\).
- FD_FWRD_INT=RVALUE

Relative design-variable change for the computation of the perturbation used for gradient evaluations. The perturbations are taken as FD_FWRD_INT times the maximum of the absolute design parameter. Default value \(=10^{-6}\).
- TOL_FEAS=RVALUE

Tolerance on feasibility conditions. An iterate is said to satisfy the feasibility conditions if \(\operatorname{FEAS}(\mathrm{x}) \leq \mathrm{TOL}_{\text {FEAS }} \times \operatorname{SIZE}(\mathrm{x})\), where \(\operatorname{SIZE}(\mathrm{x})\) represents a scaling quantity taking into account the norm of the solution vector. Default value is \(10^{-6}\).
- TOL_GRAD=RVALUE

Tolerance on the measure of criticality of the current iterate. An iterate is said to be critical if \(\operatorname{OPTIM}(\mathrm{x}) \leq \operatorname{TOL}_{\mathrm{GRAD}} \times \operatorname{SIZE}(\lambda)\) where \(\operatorname{SIZE}(\lambda)\) is a scaling factor representing the sensibility of the current solution with respect to changes of problem data. Default value is \(10^{-4}\).
- PRN_MAJOR=YES |NO

Controls the output of the optimization algorithm. Several lines of informations are written to the otm file during the optimization process. This output is a structured file that can be examined with the viewotm script. When set to no, the information will not be written to the file. Default is yes. For more information please refer to "Exploiting Output Results" on page 1190.
- PRN_MINOR=YES|NO

Controls the output of the optimization algorithm at a low level of description. A large amount of information is written to the .qtm file at each major iteration. This file does not reveal proprietary informations about the user's problem. It describes only the optimization run, and is dedicated to support. The structure of this file may change significantly between releases, it is strongly recommended to not base scripts or wrappers on this file. Default is no.

\section*{Eldo Optimizer/Search Arguments}

When method=search the Search method is launched. This method can be controlled with the following arguments:
- MAX_ITER=IVALUE

Maximum number of iterations allowed for the algorithms.
- TOL_RELPAR=RVALUE

Convergence criterion on the relative variation of the optimization variables. Note that this argument exists for the Secant/Dichotomy/Passfail methods. The stopping test is implemented as follows. We measure the relative change in x by the quotient:
\[
\text { relx }=\frac{\left|x_{\text {new }}-x_{\text {cur }}\right|}{\max \left\{\left|x_{\text {new }}\right|, \operatorname{typ} x\right\}}
\]
where \(x_{\text {new }}\) is the new value of the variable, \(x_{\text {cur }}\) is the current value of the variable, and typx is the nominal or typical value of \(x\) (which is computed dynamically). The test is satisfied if one has:
\[
r e l x \leq T O L_{R E L P A R}
\]

For the selection of tol_Relpar one could adopt the basic rule: if \(p\) significant digits of the optimal solution are desired, тOL_RELPAR should be set to \(10^{-\mathrm{p}}\). The default value is \(10^{-3}\).

\section*{Eldo Optimizer/Dichotomy/Secant/PassFail Arguments}

The optimization specification acting on one-dimensional problems is achieved by specifying the argument method=dichotomy \(\mid\) Secant \(\mid\) PASSFAil. The following is a list of arguments that are supported with these algorithms:
- MAX_ITER=IVALUE

The maximum number of iterations allowed for the algorithms.
- TOL_RELPAR=RVALUE

Convergence criterion on the relative variation of the optimization variables. The optimization is stopped when the relative change at the current iteration is approximately less than tol_relpar. This test is performed with:
\[
\text { relx }=\frac{\left|x_{\text {new }}-x_{\text {cur }}\right|}{\left|x_{u}-x_{l}\right|}
\]
and the algorithm is stopped when:
\[
r e l x \leq T O L_{R E L P A R}
\]

Default value is \(10^{-3}\).
- TOL_RELTARG=RVALUE

Convergence criterion on the relative change of the design objective. This test is performed with:
\[
\left|f\left(x_{\text {new }}\right)-f\left(x_{\text {cur }}\right)\right| \leq \operatorname{TOL}_{\text {RELTARG }} \cdot\left|f_{\text {GOAL }}\right|
\]
where \(\mathrm{f}_{\mathrm{GOAL}}\) is the goal value. Default value is \(10^{-3}\).

\section*{Note}

The previous convergence tests have some drawbacks. For example, the last one is never satisfied when the goal value is exactly zero (except when \(f\left(x_{\text {new }}\right)=f\left(x_{\text {cur }}\right)\) ). A future release will correct this issue.
- LIMIT=PASS \(\mid\) FAIL

Only used with the Passfail method. If limit is set to PASS (default), the last iteration is always the one for which the measurement is correct. If LIMIT is set to FAIL, the last iteration will be the one for which the measurement fails.

\section*{.PARAMOPT}

The specification of the optimization variables is realized with an extension of the .PARAM command. These variables will be denoted by a vector of real values of dimension N :
\[
\mathrm{x}=\left(\mathrm{x}^{(1)}, \mathrm{x}^{(2)}, \ldots, \mathrm{x}^{(\mathrm{N})}\right)
\]

The vector x is also associated with vectors of the lower and upper bounds denoted by \(\mathrm{x}_{1}, \mathrm{x}_{\mathrm{u}}\). An additional vector \(\delta\) will be associate to the discretization (or resolution) of the variables x .

\section*{Command Syntax}

The design variables must be specified through the .PARAMOPT command:
```

.PARAMOPT VARIABLE_NAME=(

+ [INIT_VALUE,]
+ {LOWER_BOUND LOWER_PERCENT% },
+ {UPPER_BOUND UPPER_PERCENT% }
+ [, INCREMENT])

```

\section*{Parameters}
- VARIABLE_NAME

Name of the design variable(s). This parameter can be one of the following:
```

PARAMETER_NAME |
P (PARAMETER_NAME) |
P (SUBCKT_NAME,SUBCKT_PARAMETER) |
E (DEVICE, PARAMETER) |
M(MODEL_NAME,MODEL_PARAMETER) |
EM(DEVICE_NAME,MODEL_PARAMETER)

```

The character strings PARAMETER_NAME, SUBCKT_NAME, and MODEL_NAME may contain wildcard characters * and ?. These features allow a group of parameters to be manipulated, rather than a unique parameter i.e. the .PARAMOPT command has two distinct behaviors; it can define the vector of design parameters x , using a component-wise specification, or a generic specification. These features are described below in Generic Specification of Design Parameters.
- initial_Value

Initial value of the design variable. It is optional in some situations, see Optional Initial Value.
- LOWER_BOUND, UPPER_BOUND

Lower and upper bounds specified for the design variable. Unbounded (or free variables) must be specified using the star character *, for example:
.PARAMOPT VAR1 \(=(1.0,0.0, *)\)
specifies a non- negative \(0 \leq \operatorname{var} 1 \leq \infty\) parameter VAR1 with the initial value set to 1.0 . Free variables \(-\infty \leq \mathrm{x} \leq \infty\) are specified using the triplet:
.PARAMOPT VARIABLE_NAME=(INIT_VALUE, *, *)
- LOWER_PERCENT\%, UPPER_PERCENT\%

Percentages of the initial value. For example, the command:
. \(\operatorname{PARAMOPT}\) VAR1 \(=(5.0,10 \%, 35 \%)\), specifies that the effective lower and upper bounds are \(\mathrm{x}_{\mathrm{l}}{ }^{(1)}=5.0 \times(1-0.1)\) and \(\mathrm{x}_{\mathrm{u}}{ }^{(1)}=5.0 \times(1+0.35)\).
- INCREMENT

Specifies a discretization for the final value of the design parameter, see Discretization of Design Variables for more information. Optional.

\section*{Caution}

The .PARAMOPT command supports fixed variables: \(\mathrm{x}_{\mathrm{l}}{ }^{(\mathrm{i})}=\mathrm{x}^{(\mathrm{i})}=\mathrm{x}_{\mathrm{u}}{ }^{(\mathrm{i})}\). For instance, it is possible to fix the number of fingers N 1 when optimizing a NMOS device by specifying: .PARAMOPT N1 \(=(30,30,30)\). The simulation time is proportional to the number of variables. For efficiency, this feature should be avoided.

For example, to optimize the length L and width \(\mathbf{w}\) of a MOS transistor, the parameter specification can be:
```

.PARAMOPT

+ L = (10U, 2U, 100U, 0.01U)
+W = (60U, 2U, 200U, 0.01U)

```

Here, the optimization is initiated with a length of \(10 \mu \mathrm{~m}\) and a width of \(60 \mu \mathrm{~m}\) The length is allowed to change between \(2 \mu \mathrm{~m}\) and \(100 \mu \mathrm{~m}\) by steps that are multiples of \(0.01 \mu \mathrm{~m}\). Similarly the width can to take values between \(2 \mu \mathrm{~m}\) and \(200 \mu \mathrm{~m}\), that differ from the initial value \((60 \mu \mathrm{~m})\) by a multiple of \(0.01 \mu \mathrm{~m}\).

\section*{Specification of Design Parameters}

Suppose that an optimization has to be performed on the following circuit:
```

.MODEL NMOD1.1 NMOS LEVEL=53

+ LMIN=0.1U LMAX=0.2U
+ WMIN=1U WMAX=100U
+ VTHO=0.2
.MODEL NMOD1.2 NMOS LEVEL=53
+ LMIN=0.2U LMAX=0.3U
+ WMIN=1U WMAX=100U
+ VTHO=0.3
.MODEL NMOD1.3 NMOS LEVEL=53
+ LMIN=0.3U LMAX=1U
+ WMIN=1U WMAX=100U
+ VTHO=0.4
VD D 0 DC 1.5
VS S O DC 0
VB B O DC 0
VG G O DC 3
RD1 D D1 1

```
```

RD2 D D2 1
M1 D2 G S B NMOD1 W=10U L=0.25U
M2 D1 G S B NMOD1 W=10U L=0.35U

```

Adding the following commands will only change the length of m 2 :
```

OPTIMIZE
.PARAMOPT E (M2,L) = (0.35U, 0.1U, 1U)

```

The length of m1 and m2 can be changed with:
```

OPTIMIZE
.PARAMOPT E (M*,L) = (*, 0.1U, 1U)

```

The initial values specified on the instances are kept unchanged. The following command will change lengths of m 1 and m 2 , the initial values are both set to \(0.35 \mu\).
```

.OPTIMIZE
.PARAMOPT E(M*,L)=(0.35U, 0.1U, 1U)

```

The following sequence of examples will affect the parameter vтно.
```

OPTIMIZE
.PARAMOPT EM (M2,VTHO)=(0.3, 0.1, 1)

```

Changes the parameter vtho of the model used by m2.

\section*{Note}

For this kind of parameter, the initial value is ignored.

Using wildcards, the parameter vтно can be changed for both m1 and m2, this can be achieved with:
```

.OPTIMIZE
.PARAMOPT EM(M*,VTHO)=(*, 0.1, 1)

```

The following commands:
```

.OPTIMIZE
.PARAMOPT M(NMOD1.3,VTHO)=(0.3, 0.1, 1)

```
and:
```

.OPTIMIZE
.PARAMOPT M(NMOD1.*,VTHO)=(0.3, 0.1, 1)

```
will change the parameter VTH0 of the model NMOD1.3 and all models NMOD1.* respectively.

\section*{Note}

For this kind of parameter, the initial value is ignored.

\section*{Optional Initial Value}

By default, the . РАRAMOPт command requires an initial value for the parameter to be optimized. However, it is possible to omit the parameter INITIAL_VALUE, and take the value that is available in the netlist. This can be achieved in two ways:
- Globally, the option paramopt_noinitial can be specified to inform Eldo that initial values are not specified. The following statement must be used:
```

.PARAMOPT VARIABLE_NAME=(

+ LOWER_BOUND, UPPER_BOUND
+ [, INCREMENT])

```
- For a single parameter, the following can be specified, and the initial value will be obtained from the netlist.
```

.PARAMOPT VARIABLE_NAME=(

+ *,
+ LOWER_BOUND, UPPER_BOUND
+ [, INCREMENT])

```

\section*{Specification of Correlated Parameters}

Element parameters can be correlated during the optimization process. The parameters are specified through the command:
```

.CORREL EXPR ELEMENT={EXPRESSION}

```

Where element can take the form of:
```

E (ELEMENT_NAME,ELEMENT_PARAMETER)
EM(ELEMENT_NAME,MODEL_PARAMETER)
M(MODEL_NAME,MODEL_PARAMETER)
PARAMETER_NAME

```

\section*{Caution}

The meaning of .correl expr is completely different to .correl in a Monte Carlo analysis.

The character string EXPRESSION can contain references to \(\mathbf{E}(), \mathbf{E M}()\) and \(\mathbf{M}()\) these quantities must be associated with the .PARAMOPT command. Therefore, in the following case, P2 will not be affected by P1:
```

C1 1 0 P1
R1 1 0 P2
.PARAMOPT P1=(1N, 0.1N, 10N)
.CORREL EXPR P2=E (C1,C)

```

In the following case, P2 will be affected by P1:
\(\begin{array}{llll}\text { C1 } & 1 & 0 & 1 N \\ \text { R1 } & 1 & 0 & \text { P2 }\end{array}\)
R1 10 P2
```

.PARAMOPT E (C1,C)=(1N, 0.1N, 10N)
.CORREL EXPR P2=E (C1,C)

```

The purpose of the .correl command is to avoid editing files when an optimization is required to be performed on a non-parametric netlist. For example:
```

* LCR Parallel Network
VIN 1 0 AC 10R2 1 2 50
R3 2 3 50K
R5 3 0 50
L1 2 3 100U
C4 2 3 1N
vIN2 a 0 AC 10
RA A B 50
RB B C 50K
RC C O 50
LA B C 100U
CA B C 1N

```
.PARAMOPT E (C4, C) \(=(1 N, 1 N, 20 N)\)
.CORREL EXPR E \((C A, C)=^{\prime} 3 * \mathbf{E}(C 4, C) /(2+1)^{\prime}\)

\section*{Discretization of Design Variables}

Figure 18-1 illustrates such a situation. The continuous box represents the feasible domain specified by the upper and lower bounds, and the black bullets are the feasible points where the final parameters are allowed to lie.

Figure 18-1. Discretization of final parameters


For example, when the lower bound is a finite number, the set of discretized points are as follows:
\[
\left\{\mathrm{x}_{\mathrm{l}}{ }^{(\mathrm{i})}, \mathrm{x}_{\mathrm{l}}{ }^{\mathrm{i})}+\delta_{\mathrm{i}}, \mathrm{x}_{\mathrm{l}}{ }^{(\mathrm{i})}+2 \delta_{\mathrm{i}}, \ldots\right\}
\]

Where \(\delta_{\mathrm{i}}>0\) is the given increment. When the lower bound is infinite ( \(\mathrm{x}_{1}{ }^{(\mathrm{i})}=\infty\) ), the grid is started from the upper bound if this one is finite. The set of discretized points is then:
\[
\left\{\mathrm{x}_{\mathrm{u}}{ }^{(\mathrm{i})}, \mathrm{x}_{\mathrm{u}}{ }^{(\mathrm{i})}-\delta_{\mathrm{i}}, \mathrm{x}_{\mathrm{u}}{ }^{(\mathrm{i})}-2 \delta_{\mathrm{i}}, \ldots\right\}
\]

When a design parameter is unbounded \(\left(\mathrm{x}_{\mathrm{l}}{ }^{(\mathrm{i})}=-\infty\right.\) and \(\left.\mathrm{x}_{\mathrm{u}}{ }^{(\mathrm{i})}=\infty\right)\), the requirement of discretization is not considered.

\section*{Caution}

In the Eldo optimizer, the obvious strategy of ignoring the requirement of discretization is used, solving the problem with real variables, and then rounding all the components to the nearest point onto the grid at the end of optimization. This strategy is not guaranteed to give solutions that are close to optimal. Increments on design parameters should only be used with design parameters for which rounding the optimized parameters is necessary. A detailed case is given in "Additional experiments" on page 1153.

\section*{Optimization Options}

The following are a list of options that are used for optimization:
- OPSELDO_ABSTRACT

Generates a summary table of simulations containing parameter and extract values for each run. This option has no effect on the .otm file, only the .chi file is affected.
- opseldo_detail

If this option is set to none, only the last run and the nominal run will be stored in the generated files (.wdb, .aex) and no other simulation information will be displayed on the standard output. When set to ALL, simulation information for all runs will be stored. Default is none. (This option was named opseldo_nodetail in pre-v6.6 Eldo versions and was not enabled.) This option only affects the standard output (which is controlled by Eldo).
- OPSELDO_NETLIST

Generates a netlist modified from the original input file, which contains the optimized parameter values but also every parameter set under \#ifdef statements.
- OPSELDO_OUTPUT

This option controls the results of the optimization for the dichotomy, secant, and passfail methods:
```

OPSELDO_OUTPUT=0

```

Prints results in a simplified format: parameter name, goal, optimized value
OPSELDO_OUTPUT=1
Prints results using the simplified format (as for opseldo_output=0) and generate a .ops0 file using the same format.

OPSELDO_OUTPUT=2
Prints results in a detailed format: parameter name, minimum value, maximum value, weight, goal, and optimized value

OPSELDO_OUTPUT=3
Prints results using the detailed format (as for opseldo_output=2) and generate a .ops0 file using the same format.
- OPSELDO_OUTER

Allows a reverse behavior of optimization and sweep simulations (.TEMP, .DATA, or . STEP). A full optimization will be performed for each set of sweep parameters. Please refer to the section "Outer and inner design parameters" on page 1170. This option should be considered as obsolete, since the outer argument on the .OPTIMIze command offers a better control over the outer parameters.
- PARAMOPT_NOINITIAL

By default, the .PARAMOPT command requires an initial value for the parameter to be optimized. It is possible to omit the parameter initial_value, and take the value that is available in the netlist. Consider the following example (the full netlist is available in the BJT optimization example):
```

* THE MODEL
.MODEL NPN NPN (
+ XTF = XTF VTF = VTF ITF = ITF
+MJS = 0.00000 PTF = 0.00000 VJS = 0.50000
+CJS = 0.00000 BF = 138.63 BR = 1.7509
+ VAF = 63.743 VAR = 22.523 IS = 3.25401E-16
+ IKF = 4.49066E-02 ISE = 3.11122E-16 NF = 0.99595
+ NE = 1.3692 IKR = 1.14501E-02 ISC = 1.48627E-15
+NR = 0.99737 NC = 1.1209 NBM = 1.00000E-03
+ RB = 294.75 RC = 14.396 RE = 4.1147
+ MJE = 0.20000 MJC = 0.20000 XCJC= 0.84276
+TF = TF TR = TR VJE = 0.85188
+ VJC = 0.67113 FC = 0.80607 IRB = 6.12980E-05
+ CJE = 2.48421E-12 CJC = 3.43125E-12 )
* DESIGN PARAMETERS
.PARAM
+ XTF=1 ITF=0.5 VTF=1 TF=3E-8 TR=1E-7

```

The statements defining the optimization variables can then be added to the netlist (or in an included file) with the following commands:
```

* OPTIMIZATION STATEMENTS
.OPTION PARAMOPT_NOINITIAL
.OPTIMIZE
.PARAMOPT
+ XTF = (0.1, 20)
+ ITF = (0.1, 5)
+ VTF = (0.1, 10)
+ TF = (1P, 1U)
+ TR = ( 1P, 1U)

```

\section*{Note}

\(\square\)The command . PARAMOPT is an extension of the .PARAM command. It means that Eldo checks for the coherent definition of parameters. If a design parameter, such as \(\mathbf{x T F}\), is redefined with the statement .PARAMOPT XTF=(1,0.1,20), the warning message "Double definition for parameter XTF" will be generated. Use the option NOWARN=46 in order to disable these messages.

\section*{Basic Examples of Circuit Optimization}

Table 18-3 gives a brief description of the basic examples used. These circuits are available in the directory: \$MGC_AMS_HOME/examples/optimizer/

Table 18-3. Basic Examples of Circuit Optimization
\begin{tabular}{|l|l|l|}
\hline Example & File name & Description \\
\hline Low noise amplifier & lnaopt.cir & Optimization using AC, Noise and SST analyses \\
\hline Fourband filter & fourband.cir & Optimization of a filter response \\
\hline MOS characterization & nmos.cir & \begin{tabular}{l} 
Double DC sweep optimization and ALTER \\
blocks
\end{tabular} \\
\hline \begin{tabular}{l} 
Robust optimization \\
using corners
\end{tabular} & aop_optim.cir & \begin{tabular}{l} 
Optimization of a 2-stages operational Amplifier \\
using ALTER blocks
\end{tabular} \\
\hline
\end{tabular}

\section*{Designing a Low Noise Amplifier (LNA)}

The Low Noise Amplifier (LNA) architecture is a fully balanced dual-gain amplifier to achieve gain, linearity, and the noise specifications for a Zero-IF receiver architecture. Output power matching is not required since the output load is given by the integrated mixer.

This example will show how the Eldo optimizer can be used for a LNA. The architecture of the LNA is based on the 2.45 GHz Switched-Gain CMOS LNA [6]. The high-gain stage is a fully balanced cascade configuration with an integrated LC tank as the load. This design reduces the Miller effect and improves isolation (-S12). The low-gain stage consists of two NMOS devices used as switches to achieve the required linearity and insertion loss.

\section*{Problem definition}

The main characteristics are: Voltage Gain (AV), Input Power Matching (S11), Noise Figure (NF), and Input Third Order Intercept Point (IIP3). The design parameters are:
- Input Network Model (cpin1, CPin2, LSIN, CSin)
- Source Inductor (associated with serial resistance)
- NMOS Width (composed of \(10 \mu \mathrm{~m}\) length fingers)

The input network consists of a serial capacitor (CSIN) used to isolate the LNA DC from the input. A \(\pi\)-network (consists of CPIN1, CPIN2, LSIN) enables simultaneous input power and noise matching. Changing the source inductor (LS) and the width of the NMOS through the number of fingers ( N 1 ) will improve noise matching, input power matching, and linearity characteristics such as IIP3 (the current and the load values are fixed to 6 mA and \(200 \Omega\) respectively).

\section*{Analyses}

Using a single testbench, different analyses were simulated to extract the following key specifications:
- An AC analysis in order to extract Return Loss and the Voltage Gain.
- A NOISE analysis for extracting the Noise Figure.
- A multi-tone SST analysis for the IIP3.
* Parameters
.PARAM VG=0.6 VD=1.8
.PARAM FUND1=2.45G FUND2=2.46G PIN=-50
.PARAM IS \(=6 \mathrm{~m}\) ROUT \(=200 \mathrm{RS}=\mathrm{LS} / 1 \mathrm{~N}\)
```

VIN IN 0 RPORT=50 IPORT=1 AC 1 FOUR FUND1 FUND2 PDBM (1,0) PIN -90

+ (0,1) PIN -90
VOUT OUT O RPORT=ROUT IPORT=2
* Analyses
.DC
.AC LIN 11 2G 3G
.SST FUND1=FUND1 NHARM1=5 FUND2=FUND2 NHARM2=5
.NOISE V(OUT) VIN 10
.SNF INPUT=(VIN) OUTPUT=(VOUT)
* Plots
.PLOT AC SDB(1,1)
.PLOT NOISE DB(SNF) DB (NFMIN)
.DEFWAVE AV_DB=VDB (OUT)-VDB (IN)
.PLOT AC W(AV_DB)

```

The . Defwave command was used to define the voltage gain (dB).

\section*{Design variables}

For the optimization analysis, each parameter has an initial value, together with lower and upper bounds. For example, the capacitor CPIN1 has an initial value of 0.1 p with lower and upper bounds of 0.10 p and 10p respectively. The variables LS and N 1 are specified using the fourth argument of the . PARAMOPT command. It means that these parameters are allowed to lie only on a discretized grid (the fourth parameter gives the step of this grid). Refer to "Discretization of Design Variables" on page 1146 for more information, and also the "Additional experiments" on page 1153 . Our problem has bound constraints on the variables:
```

.PARAMOPT

```
```

+ CPIN1=(0.1P,0.10P,10P)

```
+ CPIN1=(0.1P,0.10P,10P)
+ CPIN2=(0.1P,0.10P,10P)
+ CPIN2=(0.1P,0.10P,10P)
+ LSIN=(0.1N,0,30N)
+ LSIN=(0.1N,0,30N)
+ CSIN=(1P,0.10P,10P)
+ CSIN=(1P,0.10P,10P)
+ LS=(0.25N,0,3N,0.25N)
+ LS=(0.25N,0,3N,0.25N)
+ N1=(30,10,50,5)
+ N1=(30,10,50,5)
\(!0.1 \times 10^{-12} \leq \operatorname{CPIN} 1 \leq 10 \times 10^{-12}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CPIN} 1 \leq 10 \times 10^{-12}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CPIN} 1 \leq 10 \times 10^{-12}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CPIN} 2 \leq 10 \times 10^{-12}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CPIN} 2 \leq 10 \times 10^{-12}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CPIN} 2 \leq 10 \times 10^{-12}\)
\(!0 \leq \operatorname{LSIN} \leq 30 \times 10^{-9}\)
\(!0 \leq \operatorname{LSIN} \leq 30 \times 10^{-9}\)
\(!0 \leq \operatorname{LSIN} \leq 30 \times 10^{-9}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CSIN} \leq 10 \times 10^{-12}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CSIN} \leq 10 \times 10^{-12}\)
\(!0.1 \times 10^{-12} \leq \operatorname{CSIN} \leq 10 \times 10^{-12}\)
\(!0 \leq \mathrm{LS} \leq 3 \times 10^{-9}\)
\(!0 \leq \mathrm{LS} \leq 3 \times 10^{-9}\)
\(!0 \leq \mathrm{LS} \leq 3 \times 10^{-9}\)
\(!10 \leq \mathrm{N} 1 \leq 50\)
```

$!10 \leq \mathrm{N} 1 \leq 50$

```
\(!10 \leq \mathrm{N} 1 \leq 50\)
```

The degenerative integrated inductor (LS) would typically come from a design kit library. In our context, it is useful to specify the unit step $(0.25 \mathrm{n})$ to obtain the optimal matching inductor.

## Design objectives and extracted measures

To specify design objectives, the keyword GOAL is used on the .EXTRACT command, this describes the ideal target that the user would like to reach for this specification with the optimization process.

```
* AC Analysis
.EXTRACT AC LABEL=AV_dB@2.4GHz YVAL(WR(AV_DB),2.4G)
+ GOAI=20
.EXTRACT AC LABEL=AV_dB@2.4GHz YVAL(WR(AV_DB),2.4G)
+ GOAI=20
.EXTRACT AC LABEL=S11_dB@2.4GHz YVAL(SDB(1,1),2.4G)
+ GOAL=-15
.EXTRACT AC LABEL=S11_dB@2.5GHz YVAL (SDB (1,1),2.5G)
+ GOAL=-15
* Noise Analysis
.EXTRACT NOISE LABEL=NF_dB@2.4GHz YVAL (DB (SNF),2.4G)
+ GOAL=MINIMIZE
.EXTRACT NOISE LABEL=NF_dB@2.5GHz YVAL (DB (SNF), 2.5G)
+ GOAL=MINIMIZE
.EXTRACT NOISE LABEL=NFMIN_dB@2.4GHz YVAL (DB (NFMIN), 2.4G)
+ GOAL=MINIMIZE
.EXTRACT NOISE LABEL=NFMIN_dB@2.5GHz YVAL (DB (NFMIN), 2.5G)
+ GOAL=MINIMIZE
```

The specified design objectives finally lead to an optimization problem having four GOAL objectives and four minimize objectives.

The optimization process stops when the accuracy on the design variables need not be improved further, or more precisely, when the current point $\bar{x}$ satisfies the optimality condition. This optimality property can be checked in the Eldo optimizer output (.otm file):

```
Optimization Results
=====================
Section 1 - Statistics and Diagnostics
---------------------------------------
    ==> Number Of Iterations 84
    Number Of Simulations 850
    Merit Function 4.8781332e+00
    Optimality 7.55e-03
    Feasibility 0.00e+00
```

The value labeled optimality was denoted by optim (x) in the definition of the .OPTIMIZe command. A small value indicates that the optimality condition is satisfied. The term Merit Function is the value of the function minimized during the optimization process. This function can be considered as a global score associated to the final iterate, i.e. it gives the distance of the final solution to the ideal solution (which may not exist). For the LNA problem, the ideal solution would have given a Merit Function value close to 4.0, since the four error functions coming from the objectives AV_DB@2.4GHZ, AV_DB@2.5GHZ, S11_DB@2.4GHZ, and S11_DB@2.5GHz would be exactly zero, and the four mINIMIZE objectives should be close to 1.0.

The design parameters found by the optimizer provide a voltage gain close to 20 dB , a return loss of 12 dB , and an IIP3 of 1.2 dBm . Note that the value of the Noise Figure (NF) is not so similar to the value of the Minimum Noise Figure (NFMIN). Thus the noise matching can be improved, however, this maybe at the expense of S11 matching. The user is invited to use different weighting numbers for each of the objectives. Table 18-4 gives the results of optimization for the GOAL objectives:

Table 18-4. Results of Optimization for GOAL Objectives

| Name | Initial Value | Current Value | Goal Value |
| :--- | :--- | :--- | :--- |
| AV_DB@2.4GHZ | 11.9 | 20.1 | 20.0 |
| AV_DB@2.5GHZ | 11.7 | 19.6 | 20.0 |
| S11_DB@2.4GHZ | -0.82 | -15.1 | -15.0 |
| S11_DB@2.5GHZ | -0.88 | -15.1 | -15.0 |

The results reported in the previous table have been obtained with the default values (1.0) of the weight arguments. The results for minimize objectives are shown in Table 18-5:

Table 18-5. Results of Optimization for MINIMIZE Objectives

| Name | Initial Value | Current Value |
| :--- | :--- | :--- |
| NF_DB@2.4GHZ | 3.03 | 1.41 |
| NF_DB@2.5GHZ | 3.06 | 1.41 |
| NFMIN_DB@2.4GHZ | 1.01 | 0.97 |
| NFMIN_DB@2.5GHZ | 1.06 | 1.03 |

## Additional experiments

As with many problems in circuit design, we noted above that some of the variables are restricted to be members of a finite set of values. These variables were LS, the NMOS source inductor, and N 1 , the number of fingers in the NMOS. It is interesting to use the LNA problem to illustrate the distinction between the two types of discrete variables that you may encounter in practical problems. Some of the techniques exposed in this section are freely adapted from the book of Gill, Murray and Wright [4].

First consider the LNA problem with respect to the variable LS: we shall assume the N1 variable fixed at its initial value $\mathrm{N} 1=30$. The problem appears to be an optimization problem with continuous variables. What makes it a mixed continuous-discrete problem is the fact that the LS inductor comes from a design kit library which restricts the values to specific sizes. Such variables are termed pseudo-discrete, since the solution to the continuous problem (in which the variables are not subject to discrete restrictions) is well defined.

The other category of discrete variables is represented by the variable N 1 . It is clearly one for which there is no physical meaning of a non-integer value. In our case, what makes the LNA problem related to a problem with continuous variables, is the definition of the NMOS model parameters used in the design kit library. For example, the parameter wr, which represents the width offset for the channel resistance (RDS) calculation, is redefined as follows:

$$
. \mathrm{PARAM} W R=\prime(\mathrm{C} 1+\mathrm{C} 2 * \mathrm{Lm}-\mathrm{C} 3 * \mathrm{~N} 1)^{\prime}
$$

The symbols c1, c2, and c3 refer to some constant factors which we do not specify here. The parameter Lm is simply the length of the transistor. This definition of the WR parameter does not use the discrete nature of the N1 parameter. During the evaluation of this expression, the value of N1 is considered as a floating number. It means that the problem is implicitly re-formulated as continuous. Note that the situation is more difficult to treat when the integer part of N 1 is used explicitly in the previous expression:

```
WR='(C1 + C2*Lm - C3*TRUNC (N1) )'
```

Such situations should be avoided as much as possible by designers.

We will now illustrate how our problem with pseudo-discrete variables can be solved by utilizing the solution of the continuous problem. The results of the optimization are summarized in the .otm file, and the information shown in Table 18-6 can be extracted:

Table 18-6. Extracted Information from .otm File

| Name | Initial Value | Final Value | Discretized value | Increment |
| :--- | :--- | :--- | :--- | :--- |
| LS | $2.5 \times 10^{-10}$ | $1.5352 \times 10^{-9}$ | $3.0 \times 10^{-9}$ | $1.5 \times 10^{-9}$ |
| CP IN1 | $1.0 \times 10^{-13}$ | 0.0 | 0.0 | 0.0 |
| CPIN2 | $1.0 \times 10^{-13}$ | $8.7506 \times 10^{-14}$ | $2.2340 \times 10^{-13}$ | 0.0 |
| CSIN | $1.0 \times 10^{-12}$ | $1.0 \times 10^{-12}$ | $1.0 \times 10^{-12}$ | 0.0 |
| LSIN | $1.0 \times 10^{-10}$ | $1.3651 \times 10^{-8}$ | $1.3651 \times 10^{-8}$ | 0.0 |
| N1 | 30 | 18.453 | 20 | 5 |

The optimal N1 value when treated as a continuous variable is 18.453 , and we may suppose the optimal discrete value is unlikely to be very different. This will be confirmed by the next two experiments. The first experiment represents a general approach for treating optimization problems with pseudo-discrete variables, while the second illustrates what we call a "well-defined" problem.

We defined N 1 as the variable that must assume one of the integer values $\{10,15,20, \ldots, 50\}$. Let ${ }_{\mathrm{N} 1} \mathrm{C}$ denote the value of N 1 at the solution of the continuous problem, which is supposed to be unique. Suppose that ${ }_{\mathrm{N} 1} \mathrm{C}$ satisfies:

$$
n_{s}<N 1^{C}<n_{s+1}
$$

The value of the merit function Fmerit at the continuous solution is a lower bound on the value of Fmerit at any solution of the discrete problem, since if the variable N1 is restricted to be any value other than ${ }^{\mathrm{N}} 1 \mathrm{C}$, the merit function for such a value must be larger than Fmerit at the continuous solution, irrespective of the other variables (LS, CPIN1, CPIN2, ...).

The next stage of this process is to fix the pseudo-discrete variables at either ns or $\mathrm{ns}_{+1}$. This choice is achieved by combining the values in Table 18-7:

Table 18-7. Combinations of N1 and LS Values

| Name | $\mathbf{s}$ | $\mathbf{s + 1}$ |
| :--- | :--- | :--- |
| N1 | 15 | 20 |
| LS | $1.5 \times 10^{-9}$ | $1.75 \times 10^{-9}$ |

The problem is then solved again, minimizing with respect to the remaining continuous variables, using the old optimal values as the initial estimate of the new solution. As shown in Table 18-8, solving the restricted problem should require only a fraction of the effort needed to
solve the continuous problem. This is because the number of variables is smaller, and the solution of the restricted problem should be close to the solution of the continuous problem.

Table 18-8. Results of Restricted Problem

| Run | $\mathbf{F}_{\text {merit }}$ | Nb Iter | Nb Simul |
| :--- | :--- | :--- | :--- |
| $\mathrm{N} 1=20, \quad \mathrm{LS}=1.5 \times 10^{-9}$ | 4.9403493 | 16 | 130 |
| $\mathrm{~N} 1=20, \quad \mathrm{LS}=1.75 \times 10^{-9}$ | 5.4893925 | 16 | 131 |
| $\mathrm{~N} 1=15, \quad \mathrm{LS}=1.5 \times 10^{-9}$ | 5.4792729 | 57 | 467 |
| $\mathrm{~N} 1=15, \quad \mathrm{LS}=1.75 \times 10^{-9}$ | 5.0082957 | 40 | 329 |

The value of the merit function Fmerit at the continuous solution is a lower bound on the restricted solutions. This value was given above and is 4.8781332 . The solution obtained for the run with $\mathrm{N} 1=20$ and $\mathrm{LS}=1.5 \times 10^{-9}$ will be a satisfactory solution. The extra computation cost in solving the additional restricted problems associated with the discrete variables is likely to be a fraction of the cost to solve the original full continuous problem. If not, this implies that the discrete solution differs substantially from the continuous solution.

The following experiment can be considered as a complete enumeration procedure, where all the possible combinations of the discrete values of N 1 and LS were tested. It is important to note that this kind of process is very costly and inefficient. It is given for the purpose of illustration.

The plot shown in Figure 18-2 has been obtained by extracting the optimal value of the merit function $\mathrm{F}_{\text {merit }}$ after solving each problem associated to a restricted problem with fixed values N1 and LS. The following statements were used:

```
.PARAM LS=0.25n
.PARAM N1=30
.STEP PARAM LS 0 3n 0.25n
.STEP PARAM N1 10 50 5
.OPTIMIZE OUTER=LS,N1
```

This information is available as follows at the end of the .otm file (some columns were removed in order to simplify the results):

| Run | Iter | Simul | Merit Function Optim | Outer Parameters |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | 22 | 177 | $5.0741859 \mathrm{e}+016.4 \mathrm{e}-04$ | LS: $0.0000 \mathrm{e}+00$ | N1: $1.0000 \mathrm{e}+01$ |
| 2 | 11 | 97 | $6.7559608 \mathrm{e}+011.5 \mathrm{e}-03$ | LS: $0.0000 \mathrm{e}+00$ | N1: 1.5000e+01 |
| 3 | 26 | 205 | $6.2095585 e+012.3 e-04$ | LS: $0.0000 \mathrm{e}+00$ | N1: $2.0000 \mathrm{e}+01$ |
| 4 | 33 | 274 | $5.2472654 \mathrm{e}+011.1 \mathrm{e}-01$ | LS: $0.0000 \mathrm{e}+00$ | N1: $2.5000 \mathrm{e}+01$ |
| 5 | 31 | 242 | $4.1993472 \mathrm{e}+019.3 \mathrm{e}-02$ | LS: $0.0000 \mathrm{e}+00$ | N1: 3.0000e+01 |

The resulting plot of the merit function shows that there is a narrow area along the line $\mathrm{N} 1=20$ where this function takes its minimal values. This means that the assumption of a well-defined problem having continuous and pseudo-discrete variables is reasonable.

Figure 18-2. Values of the merit function


## Fourband Filter Optimization

This simple example (which first appeared in the former optimization software Opsim) illustrates the fitting of a filter response.

This problem consists of the optimization of a set of eighteen circuit parameters such that the voltage at node 12 follows the curve response given in Figure 18-3. The initial response is also plotted.

Figure 18-3. Response of the filter


## Design variables

The design variables are some resistor and capacitor values of the circuit. The initial (or nominal) values are given below. The capacitors CT, CLC, and CPASS have been specified separately in order to illustrate the effect of the initial conditions on the optimizer. Please refer to the section "Global and Local Optimization" on page 1176 for more information.

```
. PARAM
+ R2=10K CL=0.01U R2B=8K
\(+\mathrm{CTB}=0.01 \mathrm{U} \mathrm{CLB}=0.01 \mathrm{U}\) R2C=12K CTC=0.002U
\(+\mathrm{R} 2 \mathrm{D}=12 \mathrm{~K} \mathrm{CTD}=800 \mathrm{P}\) CLD=150P
\(+\mathrm{CACT} 1=0.02 \mathrm{U}\) CACT2=0.02U
+ RPASS \(=4 \mathrm{~K}\) RACT1 \(=50 \mathrm{~K}\) RACT2 \(=180 \mathrm{~K}\)
.PARAM CT=0.02U CLC=0.001U CPASS=0.3U
```

with the associated .PARAMOPT statements:

```
.PARAMOPT
+ R2 = ( 5K, 20K)
+ CT = (0.001U, 0.05U)
+ CL = (0.001U, 0.05U)
+ R2B = ( 3K, 10K)
+ CTB = (0.001U, 0.05U)
+ CLB = (0.001U, 0.05U)
+ R2C = ( 5K, 20K)
+ CTC = (0.001U, 0.01U)
+ CLC = (0.001U, 0.005U)
+ R2D = ( 5K, 20K)
+ CTD = ( 100P, 1000P)
+ CLD = ( 10P, 500P)
+ CPASS = ( 0.1U, 1.0U)
+ CACT1 = (0.001U, 0.05U)
```

```
+ CACT2 = (0.001U, 0.05U)
+ RPASS = ( 1K, 5K)
+ RACT1 = ( 20K, 100K)
```


## Analyses

A single AC analysis is performed, this is driven by .DATA command.

```
.AC DATA=DATA_FOURBAND
.DATA DATA_FOURBAND
+ FREQ VDB12
+ 1.122E+02 -8.326E+00
+ 1.166E+02 -7.435E+00
+ 1.212E+02 -6.566E+00
+ 8.913E+04 -4.212E-01
+ 9.261E+04 -4.213E-01
+ 9.624E+04 -4.215E-01
.ENDDATA
```


## Design objectives

The optimization will be performed on a single design objective to improve the match of the constructed model (or the target curve) with the actual measurements. The differences between the model and the measured values are combined in a global error function (using the least squares approach). The objective statement is as follows:

```
.OBJECTIVE AC LABEL=RESPVDB12
+ VDB(12) GOAL=DATA_FOURBAND(VDB12)
```

Former releases of the Eldo optimizer used the equivalent (but less explicit) fitting construct:

```
.EXTRACT AC LABEL=RESPVDB12 FITTING
```

+ DATA_FOURBAND (VDB12) VDB(12)


## Optimization results

The values shown in Table 18-9 can be found in the file fourband.otm generated during the optimization process. The optimization was performed on a 32-bit Linux machine.

Table 18-9. Values Extracted from fourband.otm File

|  | Minimum Error | Global Error | Maximum Error |
| :--- | :--- | :--- | :--- |
| Test 1 | $1.7 \times 10^{-6}$ | $1.6 \times 10^{-6}$ | $7.3 \times 10^{-3}$ |
| Test 2 | $1.4 \times 10^{-4}$ | $1.2 \times 10^{-2}$ | $4.3 \times 10^{-1}$ |

The minimum and maximum errors give the range of the residuals (difference between the target and the measured values) after optimization. The global error represents the error
function minimized by the optimizer (this value may differ with the merit function of the optimizer). The optimized response is not plotted in Figure 18-3 since the target and the output responses are the same.

Figure 18-4. Optimized response (starting from a different point)


Now consider the following initial values of the capacitors CT, CLC, and CPASS:

```
.PARAM CT=0.002U CLC=0.0001U CPASS=1.0U
```

The corresponding response is plotted in Figure 18-4 and the minimum and maximum errors are stored in previous table.

This example illustrates the influence of the initial point in circuit optimization and the relative robustness of the optimizer. The second test is much more difficult to solve.

## MOS Characterization

This example illustrates the combination of a double DC sweep and ALTER blocks for the optimization of I-V data for a Level 3 MOS model. The data consists of drain characteristics (IDS versus VDS and VGS) with two different choices of the length parameter L .

The data is stored in two separate .DATA statements (d25x25.dat and $d 25 x 2 p 5$.dat files). The I-V curves are shown in Figure 18-5 at the initial point of optimization.

Figure 18-5. Illustration of I-V characteristics


## Circuit statements

The circuit and the model statement are given below. The circuit is a simple single transistor circuit. The parameter VDS, VGS and VBS are the names of the sweep parameters used in the parametric DC analyses.
.MODEL NMOS NMOS (LEVEL=3 TOX=2.0E-8 NSUB=1E16

+ LD=LD VTO=VTO GAMMA=GAMMA UO=UO VMAX=VMAX
+ THETA=THETA ETA=ETA KAPPA=KAPPA)


## ALTER blocks and design objectives

In our example the netlist consists of two blocks, the second is defined with a .ALTER command. It is important to understand that the first . objective command has a local scope. This means that the expression $I(V 101)$ is computed in a specific simulation context. This context is related to a ALTER block (the first block may be considered as the root block or nominal case).

```
* DRAIN CHARAC W=25U L=25U AT VBS=0.0
.INCLUDE d25x25.dat
.DC DATA=DATA_D25X25 ! DATA DRIVEN ANALYSIS
.OBJECTIVE DC LABEL=FIT_IDRAIN I(V101) ! DOUBLE DC SWEEP OPTIMIZATION
+ GOAL=DATA_D25X25(IDS) TYPVAL=1E-4
```

```
* DRAIN CHARAC W=25U L=2.5U AT VBS=0.0
.ALTER DRAIN 25X2P5 AT VBS=0
M25X25D1 101 102 0 103 NMOS W=25U L=2.5U NRS=0.12 NRD=0.12
.INCLUDE d25x2p5.dat
.DC DATA=DATA_D25X2P5
.OBJECTIVE DC LABEL=FIT_IDRAIN I(V101)
+ GOAL=DATA_D25X2P5(IDS) TYPVAL=1E-3
```

The argument typai has been used to globally rescale the objectives (the extracted measures and the associated target values), such that the low current data is not dominated by others data.

## Design variables

This example performs optimization of the level 3 parameters: LD, VTO, GAMMA, UO, VMAx, theta, eta, and kappa. The corresponding statements are:

```
.PARAM
+ LD=1E-7 VTO=1.0 GAMMA=0.6 UO=600 VMAX=1E5
+ THETA=0.1 ETA=0.01 KAPPA=1
.OPTION PARAMOPT_NOINITIAL
.PARAMOPT
+ LD = ( 1E-9, 5E-7)
+ VTO = ( 0, 2)
+ GAMMA = ( 0.1, 2)
+ UO = ( 300, 900)
+ VMAX = ( 1E4, 1E7)
+ THETA = ( 1E-6, 2)
+ ETA = (1E-4, 2)
+ KAPPA = (1E-6, 1E3)
```


## Optimization results

The values presented in Table 18-10 can be found in the nmos.otm file generated during the optimization process. The optimization was performed on a 32-bit Linux machine.

Table 18-10. Values Extracted from nmos.otm File

|  | Minimum Error | Global Error | Maximum Error |
| :--- | :--- | :--- | :--- |
| Length L=25U | 0.0 | $1.1 \times 10^{-18}$ | $3.5 \times 10^{-9}$ |
| Length L=2.5U | 0.0 | $6.4 \times 10^{-17}$ | $3.0 \times 10^{-8}$ |

Note that these values are the result of a synthetic problem. The circuit parameters were fixed, the data was then generated, and the circuit was optimized after performing a perturbation of the initial point. This is why the global error is so small. The residuals are almost zero. This is not the case with realistic data where the physical measurements involve some variability in the current curves.

## Robust Optimization Using Corners

This example illustrates the combination of optimization and .ALTER commands. For this purpose a new architecture based on the concepts of multi-context of simulation and multinetlist optimization has been developed.

## Problem definition

Nominal optimization focuses on finding the best design parameters for one nominal operating condition of the circuit. Typically the power supply, the ambient temperature, and the process technology are given their nominal value, and the best set of design parameters is found by the optimizer, given its targets. If the circuit has to operate under a variety of operating conditions, nothing guarantees that this will still be the case, if the design parameters are simply set to these optimal nominal values. Maybe if the power supply level is slightly changed, the circuit will fail.
'Robust optimization' focuses on finding the 'best' set of parameters that fulfill the specifications across a certain range of operating conditions. For example, robust optimization would be performed on a circuit that must operate between 1.7 and 1.9 V , a temperature range of -25 C to 100 C , and accommodate variations in the process (defined by the 'corner' device model libraries). In this case the optimization targets might be upper or lower bounds on certain characteristics (for example the DC consumption has to be 'lower than $50 \mu \mathrm{~A}$, in all operating conditions). Targets can be set as targets for the average value of a given specification.

Operating conditions are conveniently defined with .ALTER commands in Eldo. In each . ALTER command, a specific combination of parameters defining the operating conditions (typically the power supply level and the temperature) and the corner device model library, can be defined. The optimization commands (design variables definition, design objective definitions, and the optimize command) from the main netlist are then interpreted to span the main netlist conditions and the various combinations defined through the .ALTER sections. Obviously these types of optimizations are usually more costly than simple nominal optimizations. Eldo can distribute the necessary simulation on multi-processor machines, thus potentially accelerating the process.

## Circuit statements



```
* 2-STAGES OPAMP - TYPICAL MODEL FOR 3.3V
M16 VDD BIAS M17D VDD PCH_33 W='WS*4.8U' L=0.8U
M17 M17D M17D VSS VSS NCH_33 W='WS*3.2U' L=0.8U
M15 M15D M17D VSS VSS NCH_33 W='WS*3.2U' L=0.8U
M13 M13D M17D VSS VSS NCH_33 W='WS*3.2U' L=0.8U
M14 VDD M15D M15D VDD PCH_33 W='WS*1U' L=0.8U
M12 VDD M13D M13D VDD PCH_33 W='WS*4.8U' L=0.8U
M3 VDD M13D M1D VDD PCH_33 W='WS*4.8U' L=0.8U
M4 VDD M13D M2D VDD PCH_33 W='WS*4.8U' L=0.8U
```

| M11 | VDD | M13D | OUT | DD | PCH_33 | W= ${ }^{\prime}$ WS*16U' |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| M1 | D | NP | OM | COM | CH_33 | W='WS*0.8U |  |
|  | M2 | NN | COM | COM | CH |  |  |
| M9 | COM | M17D | SS | S | NCH | W | L |
| M5 | M2D | M15D | M7D | VDD | PCH_33 | W='WS*2 | $\mathrm{L}=0.8 \mathrm{U}$ |
| M6 | M1D | M15D | M8D | VDD | PCH_33 | W='WS*2.4U | L=0 |
|  | M7D | 7 D | VSS | VSS | NCH_33 | W='WS*1 | $\mathrm{L}=0.8 \mathrm{U}$ |
| M8 | M8D | M7D | VSS | VSS | NCH_33 | W='WS*1.6U | L= |
| CX | M8D | OUT | C_COMP ! LOUSY COMPENSATION CAP. |  |  |  |  |
| CL | OUT | 0 | 1 P ! LOAD CAP. |  |  |  |  |
| M10 | OUT | M8D |  |  |  |  |  |

```
.CONNECT OUT INN ! FOLLOWER CONNECTION
```

. OP
.TRAN 1N 400N
.PLOT TRAN V(INP) V(OUT)
.OPTION TUNING=VHIGH NOASCII NOMOD

```
VDD VDD 0 1.65V
vSS VSS 0 -1.65V
VB BIAS 0 0.55V
* TYPICAL MODEL FOR 3.3V DEVICES
.LIB ./cln90g_lk.eldo TT_33
```

VINP INP 0 PULSE -0.90 .9 10N 1N 1N 200N 400N AC 10

## .ALTER sections

```
The following corners are used:
* SS_33 : Slow NMOS Slow PMOS model for 3.3V devices
.ALTER SS_33 : SLOW NMOS SLOW PMOS MODEL
.LIB ./cln90g_lk.eldo SS_33
* FF_33 : Fast NMOS Fast PMOS model for 3.3V devices
.ALTER FF_33 : FAST NMOS FAST PMOS MODEL
.lib ./cln90g_lk.eldo FF_33
* SF_33 : Slow NMOS Fast PMOS model for 3.3V devices
.ALTER FS_33 : FAST NMOS SLOW PMOS MODEL
.LIB ./cln90g_lk.eldo FS_33
* FS_33 : Fast NMOS Slow PMOS model for 3.3V devices
.ALTER FS_33 : SLOW NMOS FAST PMOS MODEL
.LIB ./cln90g_lk.eldo SF_33
```


## Analyses and design objectives

Two analyses were specified to define the following design objectives:

- A transient analysis in order to extract the output voltage.
- A DC analysis for extracting the IDS current.

```
.EXTRACT TRAN LABEL=RSLOPE SLOPE (V (OUT),0,0,140N)
+ GOAL=80.0E6 WEIGHT=1000.0
.PARAM SCAL_I=1E4 ! INVERSE OF TYPICAL VALUE
.EXTRACT DC LABEL=SCAL_IBIAS SCAL_I*ID(M16)
+ GOAL=MINIMIZE WEIGHT=1.0
```

The constant parameter SCAL_I was used in order to rescale the extracted measure IBIAS. The values taken by RSLOPE and SCAL_IBIAS have the same order of magnitude. The specified weight for the measure RSLOPE was introduced to find a solution that minimize the rise time at the expense of larger IBIAS values. Users can experiment with different choices of weights.

## Design variables

A shrink parameter ws is used for the width of each MOS instantiated in the netlist. The capacitor is also optimized:

```
.PARAMOPT
+ WS=(2,0.5,4)
+ C_COMP=(1p,0.01p,100p)
```


## Optimization results

This example must be run with the following commands:

```
.OPTIMIZE TOL_OPT=1E-2
.OPTION OPSELDO_ALTER
```

where the option opseldo_alter informs Eldo that optimization must be performed on all . alter sections. The results of the optimization are placed in the optimization file with the extension .otm.

## Set-up Time Computation

The goal here is to use Eldo to compute the set-up time of a flip-flop. The definition of set-up time is: time between input and the clock (TIC) so that propagation time between clock and output (TCO) is $10 \%$ above nominal value (computed when there is a large time between input and the clock).

To do this, suppose that the nominal value of T со is already known.

## TCO_TARGET $=1.1 \times$ TCO_NOMINALS

A very general method, available even with older versions of Eldo, would be to sweep TIC, measure TCO, and extract from TCO (TIC) the value of TIC so that TCO=TCO_TARGET.

```
.PARAM TIC=200n
.STEP PARAM TIC 205N 195N 0.1N
.EXTRACT LABEL=TCO
+ (XUP(V(Q),0.48,200n,300n,1) - XUP(V(CP),0.48,200n,300n,1))
```

```
.EXTRACT SWEEP xycond(XAXIS, meas(TCO)=1.1*TCO_NOMINAL)
```

Simulation time can be improved with the use of . OPtion autostop=2. Accuracy is proportional to the parameter sweep increment, and simulation time is proportional to the number of steps in the swept interval. From Eldo v5.8, it is possible to use two new methods of optimization that are suitable for the computation of set-up the time. The passfail method computes the maximum value for which an extract can be measured. This is not exactly the definition of set-up, however, it can be used as a first step, this would give:

```
.OPTIMIZE METHOD=PASSFAIL RESULTS=TCO
.PARAMOPT TIC=(201N,199N,205N)
```

The diснотому method, finds the value of an optimization parameter so that one extract yields a target value, provided that the extract values for the Min and Max values of the optimization parameter bracket the target.

In this example, the Min value of the optimization parameter TIC has been computed with the PASSFAIL method, this will give:

```
.EXTRACT TRAN LABEL=DCP
+ (XUP(V(Q),0.48,200N,300N,1) - XUP(V (CP),0.48,200N,300N,1))
+ GOAL={1.1*TCO_NOMINAL}
.PARAMOPT TIC=(201N,200.07N,205N) !MIN provided by PASSFAIL
```

From Eldo v5.9, it is possible to combine both passfail and dichotomy methods in one step with the following syntax:

```
.OPTIMIZE METHOD=DICHOTOMY
.EXTRACT tran LABEL=DCP
+ (XUP(V(Q),0.48,200N,300N,1) - XUP(V (CP),0.48,200N,300N,1))
+ GOAL={1.1*TCO_NOMINAL }
.PARAMOPT TIC=(201N,195N,205N)
```

The secant method search algorithm is more advanced than the dichoтому method. Many problems suitable for bisection (one design parameter, one target) are actually relatively linear, i.e. the target value is almost proportional to the design parameter. In these conditions, using the длснотому method is clearly sub-optimal in terms of the number of iterations required. Using the SECANT method will greatly diminish the number of iterations. This feature is useful for designers that want to accelerate their setup/hold simulations.

## Modeling Capabilities in Eldo and Optimization

The optimization functionality implemented in the Eldo optimizer are designed to match as much as possible the modeling capabilities available through the Eldo language. As described in the introduction, the designer's request for optimization, the definition of the parameters to be optimized, the design objectives that they should satisfy are specified in the netlist file, by using simple extensions of the Eldo commands.

The simulator is regarded as a black box that provides a vector of measures $F(x)$ given the set of design variables x, shown in Figure 18-6.

Figure 18-6. Simulator as black box


In general, the choice of the optimization parameters does not lead to severe difficulties. It is part of the designer's knowledge about the circuit, while it is not necessarily the case with the definition of the design objectives to be optimized (the function $\mathrm{F}(\mathrm{x})$ ). Here is a list of issues associated to the question of the appropriate model for optimization:

- What kind of problems can be solved using the Eldo language constructs such as multiple sweep commands or step increments on parameters? How are Alter blocks handled in the context of optimization? These groups of issues are related to the mathematical formulation of the optimization problem.
- What are the common issues related to the built-in functions used in the extraction of measures? For instance, a difficult situation arises when the design objectives are not continuous functions and/or do not have continuous derivatives.
- The mathematical issues that are peripheral in the problem of circuit design have to be considered, but essential to the computer solution of actual problems. That is how to adjust for problems that are badly scaled in the sense that the optimization variables or the design objectives are of widely differing magnitudes. It is also necessary to consider how to determine when to stop the iterative algorithms (used in the Eldo optimizer) in finite-precision arithmetic.

When optimizing a circuit, the mathematical aspects are not great concern. The user can avoid technical details, accepting when some explanations are required for better use of these optimization features.

## What Problems can be Solved?

## Representation of design objectives

This section is organized as follows:

- The notions of design parameters and design variables. These concepts are formal, but necessary in order to get a good view of the modeling capabilities.
- How to perform a sequence of optimizations while sweeping one or more circuit parameters.
- The specifications of design variables and design objectives are explained in detail.


## Notions of design variables and design parameters

It is useful to consider circuit parameters separately that are the candidate for optimization (such as width and length for MOS) and those associated to DC multi-point, transient, small signal, frequency, or parametric analysis. The former ones will be denoted as design variables and the latter as design parameters (or sweep parameters).

Design variables are only specified through the .PARAMOPT command. They represent the vector of variables $x$. Optimization will always occur with respect to these variables. Conversely, the design parameters represent the values of a user-defined discretization of a realvalued set $\Omega$. Those parameters are denoted by the Greek letter $\omega$.

For example, the Voltage-Temperature parameters temperature-voltage (TEMP,PVDD):

```
.STEP TEMP -25 150 5
.STEP PARAM PVDD 2.7 3.3 0.1
```

define a cartesian product or a box $\Omega=[-25,150] \times[2.7,3.3]$ in the 2-dimensional space $\mathfrak{R}^{2}$. The design parameters have various origins, however, they are usually defined through sweep simulations. The way the box $\Omega$ can be discretized follows the capabilities offered by the using .TEMP, .DATA and .STEP commands.

The following characterization can shed some light on the role of $x$ and $\omega$ :

- the task of evaluating the extracted measures remains in the hands of the simulator, and the optimizer is only required to provide a new approximate solution x .
- It means that the parameters $\omega$ are only varying within the simulator, while the design variables are only affected by the optimization algorithm. The simulation and the optimization processes are totally distinct.

The example of a 2-dimensional domain $\Omega$ can be considered, as shown in Figure 18-7, and obtained from a multi-step specification:

```
* Design parameters
.STEP PARAM OMEGA_1 <INCR_SPEC_1>
.STEP PARAM OMEGA_2 <INCR_SPEC_2>
* Minimization of the design objective: f
. OBJECTIVE
+ EXTRACT_INFO LABEL=F
+ {$MACRO|FUNCTION}
+ GOAL=MINIMIZE
```

The argument goal=minimize specifies that the extracted measure f must be minimized with respect to the variables x .

Figure 18-7. Discretization of design parameters


Due to the presence of the multiple increments on $\omega$, the extracted measure $f$ is a bi-dimensional object of size defined by the range of the . STEP statements. Given the values of the variables $x$ (fixed during one single simulation), the simulator returns a value $f=f\left(x ; \omega^{(1)}, \omega^{(2)}\right)$ for each discretized point $\left(\omega^{(1)}, \omega^{(2)}\right)$.

The argument GOAL=MINIMIZE on the extracted measure finally means that the whole set of values of f must be minimized with respect to x .

## Explicit and implicit design parameters

When optimizing a circuit, the category of design parameters can be divided into explicit and implicit parameters. For the transient and the small-signal analyses the time and frequency, respectively, are clearly implicit parameters.

To specify a quiescent analysis (that is a component analysis CNAM), a voltage or current analysis (SNAM), a temperature analysis, and a parameter analysis the following can be specified:

```
.DC CNAM [L|W] START STOP INCR
.DC SNAM START STOP INCR [SNAM2 START2 STOP2 INCR2]
.DC TEMP START STOP INCR
.DC PARAM START STOP INCR
```

the parameters are always considered as implicit. In the context of optimization, Eldo will run the specified analyses with their nominal values (defined in the netlist).

An important exception is the DC analysis that is driven by a .DATA construct:
.DC DATA=DATA_SWEEP

## Hierarchy and depth of design parameters

The modeling capabilities of Eldo allow various specifications of design parameters. In the following the hierarchy (or the default order of precedence) of the commands that define the variation of the parameters are given:

- Several .alter blocks with the label denoted by $\mathrm{A}_{1}, \mathrm{~A}_{2}, \ldots$
- A .TEMP command or a .step command on temperature

```
.TEMP T1 T2 ...
.STEP TEMP T_START T_STOP T_INCR
```

- A . Step command using different variants of libraries (or corners K):
.LIB mylib TYP
.STEP LIB (mylib) K1 K2 ...
- A . step command on circuit parameters
.STEP PARAM ALPHA ALPHA_START ALPHA_STOP ALPHA_INCR
- Multiple sweeps or nested sweeps on parameters, and a parameter sweep in the analysis command. These parameters will be denoted by $\alpha, \beta, \ldots$ The cases of dc, Ac, and tran analyses are represented by the command syntax:

```
.{AC | TRAN} <SIMUL_POINTS> SWEEP DATA=DATA_SWEEP
.DC <SOURCES/PARAMETERS/...> SWEEP DATA=DATA_SWEEP
```

where a two parameter sweep is defined with:

```
.DATA DATA_SWEEP ALPHA BETA
+ ALPHA1 BETA1
+ ALPHA2 BETA1
+ ALPHAM BETA1
+ ALPHA1 BETA2
...
+ ALPHAM BETA2
+ ALPHAM BETAP
.ENDDATA
```

- A DC data-driven analysis:
.DC DATA=DATA_SWEEP
- Transient and frequency analyses. The time and frequency parameters will be denoted by the symbol $\omega$.

It follows that a design objective $F$ can be represented as a family of real-valued functions of variables $x$. This family is parameterized with points that were denoted by $A, T, K, \alpha, \beta, \ldots, \omega$.

The following convention is used: the parameter omega is the "inner-most" and the .alter label A is the "outer-most". This convention tries to fit the order of simulations. The simulator provides to the optimizer this hierarchy for specifying the depth of a design parameter. This is used in printing routines and optimization algorithms. It is possible to change the depth of a design parameter when it is necessary, please refer to "Outer and inner design parameters" on page 1170 for more information. This feature is limited to the parameters defined in a .STEP PARAM or .STEP TEMP command.

At the same hierarchical level, the design parameters have an order of precedence defined by the simulator. For example, when the netlist contains the following statements, the parameter $\alpha$ will be the "outer-most" and $\beta$ the "inner-most":

```
.STEP PARAM ALPHA <INCR_SPEC_ALPHA>
.STEP PARAM BETA <INCR_SPEC_BETA>
```


## Outer and inner design parameters

The opseldo_outer option allows a reverse behavior of optimization and sweep simulations. It is possible to specify whether the complete set of design parameters defined through a .STEP PARAM is 'outer' or 'inner'.

Figure 18-8. Effect of the OPSELDO_OUTER option


Consider the following minimization problem with respect to the $x$ variable, where the design parameter $\omega$ belongs to the interval $\Omega=\left[\omega_{\text {start }}, \omega_{\text {end }}\right]$. A formal circuit formulation could be:

```
.PARAMOPT X=(XINIT, XL, XU)
.STEP PARAM OMEGA OMEAG_START OMEGA_END OMEGA_INCR
. OBJECTIVE
+ EXTRACT_INFO LABEL=f
+ {$MACRO|FUNCTION}
+ GOAL=MINIMIZE
.OPTIMIZE
```

The strings XINIT, XL, and XU represent, the initial value of the design variable x , its lower bound (or the minimum value that x can take) and respectively its upper bound. Please refer to ".PARAMOPT" on page 1142 for more information.

The previous optimization statements can be understood in two different ways:

- By default, the design parameter $\omega$ is always handled as 'inner'. It means that the optimizer will seek the smallest value of the function:

$$
\sum_{\omega_{i} \in \hat{\Omega}} f\left(x, \omega_{i}\right)
$$

such that the value of x is within the interval $\left[\mathrm{x}_{1}, \mathrm{x}_{\mathrm{u}}\right]$. This case is represented in the right branch of Figure 18-8.

- When the opseldo_outer option is active, the sweep on the design parameter $\omega$ becomes external with respect to the optimization process. A sequence of optimizations is launched, one for each of the discretized values within the interval $\Omega=\left[\omega_{\text {start }}, \omega_{\text {end }}\right]$.


## Note

When the opseldo_outer is active, an 'outer' sweep is performed on the complete set of the parameters involved in the . STEP, .DATA and .TEMP commands. The 'outer' and 'inner' design parameters can not be specified at the same time.

## Choice of inner and outer parameters

It is possible to specify whether a design parameter defined through a .STEP PARAM is outer or inner.

The command syntax is a simple extension of the .OPTIMIZE command:

```
.OPTIMIZE
+ [QUALIFIER=VALUE {, QUALIFIER=VALUE}]
+ [PARAM=LIST_OF_VARIABLES|*]
+ [RESULTS=LIST_OF_MEASURES|*]
```

+ [OUTER=LIST_OF_PARAMETERS|*]
There are some rules associated to this argument:
- By default, the parameters specified with a . PARAM command are inner.
- The order specified within the list of parameters LIST_OF_PARAMETERS has no precedence with respect to the implicit order specified in the netlist.
- For backward compatibility, when the opseldo_outer is active, all the parameters are outer. The list of parameters following the argument OUTER are not considered.
- This feature is not valid for the . STEP commands using variants of a library (corners), temperature sweeps.

For example:

```
.OPTION OPSELDO_OUTER
.STEP PARAM P1 <INCR_SPEC>
.STEP PARAM P2 <INCR_SPEC>
```

Both parameters are outer parameters:

```
.STEP PARAM P1 <INCR_SPEC>
.STEP PARAM P2 <INCR_SPEC>
.OPTIMIZE OUTER=P2
```

The parameter P 2 is the only candidate for the outer loop. If the arguments of the .OPTIMIZe command were as follows. OPTIMIZE OUTER=P2,P1 then the parameter P1 would still be the 'outer-most' within the outer loop, since this order is specified by the order of . Step param commands.

## Specification of multi-points simulations and optimization

The commands that designers can use in order to specify objectives based on multi-point simulations are described in this section. These simulations are the small-signal analysis (. Ac) and the transient analysis (.TRAN). The following specifications do not apply for DC-based design objectives.

Some restrictions are introduced to maintain a reasonable connection between the statements of simulation (.AC and .TRAN commands) and the optimization objectives (. OBJECTIVE command). These limitations are based on two different categories of multi-point analyses:

- .tran analysis can have implicit specification of simulation points, for example:
.TRAN TPRINT TSTOP [TSTART [HMAX]]
The simulation points are not defined explicitly, since Eldo computes simulation points for accuracy purposes.
- .tran and . AC can have explicit specification of simulation points, for example: . TRAN DATA=DATA_NAME

The explicit case is certainly the most favorable one since the simulation and the optimization commands can refer to the same list of data. Former versions of the Eldo optimizer used to interpolate measures when the simulation points were implicit. Since this technique introduces additional errors that cannot be bounded, and gives non smooth (or noisy) measurements, the default behavior is: when optimization is required, the simulation points (frequency and time) must be included in the set of simulation points.

These limitations are specifically related to the algorithm implemented in the Eldo optimizer/SQP, which cannot cope well with noisy function values (as many algorithms based on Newton iterations). For more information please refer to the section "Smooth and nonsmooth problems" on page 1175.

## Rules for implicit specification of simulation points

The implicit specification of simulation points appear in transient analyses that use the following statements:

```
.TRAN TPRINT TSTOP [TSTART [HMAX]] [SWEEP DATA=data_name]
.TRAN TPRINT TSTOP [TSTART [HMAX]]
+ [SWEEP PARAM_NAME TYPE NB START STOP]
.TRAN TPRINT TSTOP [TSTART [HMAX]]
+ [SWEEP PARAM_NAME START STOP INCR]
```

It is not possible to specify design objectives that refer to such a category of analyses.

## Rules for explicit specification of simulation points

The parameter driven and list . AC analysis, and .TRAN analysis in -compat mode is considered first. These situations match the following statements:

```
.AC TYPE NB FSTART FSTOP [SWEEP DATA=DATA_NAME]
.AC TYPE NB FSTART FSTOP [SWEEP PARAM_NAME TYPE NB START STOP]
.AC TYPE NB FSTART FSTOP [SWEEP PARAM_NAME START STOP INCR]
.AC LIST {LIST_OF_FREQUENCIES} [SWEEP DATA=DATA_NAME]
.AC LIST {LIST_OF_FREQUENCIES} [SWEEP PARAM_NAME TYPE NB START STOP]
.AC LIST {LIST_OF_FREQUENCIES} [SWEEP PARAM_NAME START STOP INCR]
.TRAN INCR1 T1 [{INCRN TN}] [TSTART=VAL] [SWEEP DATA=DATA_NAME]
.TRAN INCR1 T1 [{INCRN TN}] [SWEEP PARAM_NAME TYPE NB START STOP]
.TRAN INCR1 T1 [{INCRN TN}] [SWEEP PARAM_NAME START STOP INCR]
```

An objective statement will satisfy the command described in section ".OBJECTIVE" on page 1134. The arguments goal, equal, lbound, ubound, weight, and typval must be a scalar value or a constant waveform.

When the waveforms are used in obJective_Info, the value of the objectives (goal and bounds) are sampled values of the waveform at simulation points, and it is possible to mix scalar and waveforms. Specifying lbound as a scalar means that this bound is global.

Now consider the data-driven .AC and . TRAN analyses:

```
.AC DATA=data_name [SWEEP DATA=data_name]
.AC DATA=data_name [SWEEP param_name TYPE nb start stop]
.AC DATA=data_name [SWEEP param_name start stop incr]
.TRAN DATA=data_name [SWEEP DATA=data_name]
.TRAN DATA=data_name [SWEEP param_name TYPE nb start stop]
.TRAN DATA=data_name [SWEEP param_name start stop incr]
```

An objective statement of GOAL or EQUAL should satisfy the following syntax:

```
.<ANALYSIS> DATA=OMEGA_DATA(OMEGA)
.DATA OMEGA_DATA OMEGA GOAL_VAl WEIGHT_VAL TYP_VAL
+ OMEAG1 GOAL_VAL1 WEIGHT_VAL1 TYP_VAL1
+ OMEGA2 GOAL_VAL2 WEIGHT_VAL2 TYP_VAL2
... ... ... ...
+ OMEGAP GOAL_VAL1P WEIGHT_VALP TYP_VALP
. ENDDATA
. OBJECTIVE
+ EXTRACT_INFO [LABEL=NAME]
+ {$MACRO|FUNCTION}
+ OBJECTIVE_INFO
+ [SCALE_INFO]
```

where the parameter OMEGA is the keyword time or freq, and

```
SCALE_INFO:=
TYPVAL=RVALUE
```

and

```
OBJECTIVE_INFO:=
{GOAL=OMEGA_DATA(GOAL_VAL) | RVALUE }
    {EQUAL=OMEGA_DATA(GOAL_VAL) RVALUE }
[ WEIGHT=OMEGA_DATA(WEIGHT) RVALUE]
[ TYPVAL=OMEGA_DATA(TYP_VAL) | RVALUE]
```

Using the same .DATA statement in the analysis and the objective statement ensures coherency of data. It is possible to specify a scalar value (denoted by RVALUE) for the goal, equal, weight, and typval arguments.

Note
When weight and typval are scalar values, they apply to all lines.

An objective statement with the arguments lbound or ubound type will satisfy the following syntax:
. $<A N A L Y S I S>$ DATA=OMEGA_DATA
.DATA OMEGA_DATA OMEGA L_VAL U_VAL WEIGHT_VAL TYP_VAL

```
+ OMEGA1 L_VAL1 U_VAL1 WEIGHT_VAL1 TYP_VAL1
+ OMEGA2 L_VAL2 U_VAL2 WEIGHT_VAL2 TYP_VAL2
+ OMEGAP L_VALP U_VALP WEIGHT_VALP TYP_VALP
.ENDDATA
```

with:

```
OBJECTIVE_INFO:=
{{LBOUND=OMEGA_DATA(L_VAL)|RVALUE } | {UBOUND=OMEGA_DATA(U_VAL)|RVALUE } }
| {LBOUND=OMEGA_DATA(L_VAL)|RVALUE} {UBOUND=OMEGA_DATA(U_VAL) RVALUE}
[WEIGHT=OMEGA_DATA(WEIGHT_VAL) | RVALUE]
```

and

SCALE_INFO:=
TYPVAL=\{OMEGA_DATA (TYP_VAL) | RVALUE $\}$

## Smooth and non-smooth problems

A difficult situation arises when the functions corresponding to the design objectives do not have continuous derivatives or are not continuous at all. In this case, methods for smooth problems (such as the Eldo optimizer/SQP algorithm) will encounter difficulties.

Figure 18-9. Examples of non smooth problems


It is assumed in the optimization problem, that the functions are continuous with continuous derivatives on some domain (or sufficiently smooth). Figure 18-9 illustrates some of these difficulties:

- The first case represents a "noisy function" with an overall "trend" plotted with dashed lines. It is related to the effect of features such as adaptive algorithms and stopping tests in iterative methods inside the simulation. Note that the "noise" is not stochastic in such
situations. The Eldo optimizer/SQP will fail to make any progress because local descent directions may point uphill.
- The second example is related to the use of functions such as $\mathrm{ABS}($.$) , MIN(.) or MAX(.)$ that are not differentiable in the common sense. These situations can represent minor difficulties when the user wants only improvement of the current solution rather than optimization at "full-blown optimality".
- In general, the last two cases will lead to serious difficulties. The "discontinuous" case probably involves functions that are not numerical in nature, or the discontinuities are the result of features such as table look-ups and switches. On the other hand, the "undefined" case may be the result of unexpected failures of the simulation or undefined extracted measures.


## Global and Local Optimization

The fastest optimization algorithms only search for a local solution at a point at which the objective function is smaller than all other feasible points in its vicinity. They don't always find the best of all such minima, that is the global solution (see Figure 18-10). The reason for this is that practical methods for finding global optima are (at present time) too expensive in all but the most specialized cases.

Figure 18-10. Different types of minima


General non-linear problems may possess local solutions that are not global solutions. Global solutions are highly desirable, however, they are usually difficult to identify and even more difficult to locate. Unless very strong assumptions are made about the functions that define the optimization problem in question, characterizations of global minima are almost impossible, so even if one is found the user may never know.

The algorithm implemented in the Eldo optimizer/SQP is based on Newton iterations. It is therefore, not able to combine local and global searches, and can only find local solutions.

## Discrete optimization

In some optimization problems, the variables only make sense if they take on integer or discrete real values. The obvious strategy of ignoring the integrality requirement, solving the problem
with real variables. Rounding all the components to the nearest integer is not guaranteed to give a solution that is close to optimal. Problems of this type should be handled using the tools of discrete optimization. The mathematical formulation is changed by adding the constraint " $x_{i}$ integer for all $i \in K$ ", where $K$ is a subset of $\{1, \ldots, N\}$.

Continuous optimization problems are easier to solve, because the smoothness of the functions makes it possible to use the objective function and constraint information at a particular point x to deduce information of the functions behavior at all points close to $x$. The same statement cannot be made about discrete problems. Where points that are close in some sense may have markedly different function values. Moreover, the set of possible solutions is too large to make an exhaustive search for the best value in this finite set. When models contain variables allowed to vary continuously and others that can attain only integer values, there are referred to as mixed-integer programming problems (MIP).

The actual Eldo optimizer can only treat Nonlinear Problems (NLP) with continuous variables. The increment argument in the PARAMOPt command is used to define a grid of "integer feasible" points with uniform steps. It should be noted that "the obvious strategy of ignoring the requirement of discretization is used, solving the problem with real variables, and then rounding all the components to the nearest point onto the grid at the end of optimization." This strategy is based on the assumption that the increment value is sufficiently small. The problem solved by the optimizer is a "continuous relaxation of the original MIP problem. The constraints of integrality on variables are simply relaxed.

## Scaling of variables and objectives

An important consideration in solving many circuit design problems is that some extracted measures or optimization variables may vary greatly in magnitude.

## Scaling of variables

For example, the user may have a minimization problem in which the first independent variable $\mathrm{x}^{(1)}$ is in the range $\left[10^{8}, 10^{9}\right] \mathrm{Hz}$ and the second $\mathrm{x}^{(2)}$ in the range $\left[10^{-7}, 10^{-6}\right]$ seconds. These ranges are referred to as the scales of the respective variables. In this section, the effect of such widely disparate scales on the algorithms is considered.

One place where scaling will effect our algorithms is in calculating the difference between iterates. In the above example, any such calculation will virtually ignore the second variable (the time). The obvious strategy of re-scaling the optimization variables is used in the Eldo optimizer/SQP; that is, change their units. For example, if the units of $\mathrm{x}^{(1)}$ are changed to Giga Hertz and the units of $\mathrm{x}^{(2)}$ are changed to microseconds, then both variables will have the range $[0.1,1]$ and the scaling problem in computing the differences will be eliminated. Notice that this corresponds to changing the independent variable to

$$
\hat{x}=D^{-1} \cdot x
$$

where D is a diagonal matrix of scaling.

The Eldo optimizer/SQP method uses an affine scaling transformation based on the values of the upper and lower bounds. If the variable $x$ satisfies the relations $1 \leq x \leq u$, one can introduce the two numbers:

$$
D=\frac{2}{u-l}, c=\frac{u+l}{u-l}
$$

that define the following transformation:

$$
\hat{x}=D \cdot x-c
$$

With this formula the transformed variable will have range $[-1,1]$. The user must set the appropriate bounds on the variable $x$ corresponds to the desired change in units, and then the algorithms operate as if they were working in the transformed variable space.

The result of this scaling procedure is described in the major output file. otm. The section in the .otm file begins with the heading "Section 2 - Scaling Transformation For Variables". Please refer to "ASCII Output for Eldo Optimizer/SQP" on page 1191 for more information.

The above scaling strategy is not always sufficient; for example, there are cases that need more appropriate methodology. Consider the following problem:

```
* Circuit Statements
    .PARAM LOGL={LOG10(150U)}
    .PARAM LOGR={LOG10(10)}
    .PARAM LOGC={LOG10(10U) }
V1 1 0 AC 1
L1 1 2 5U
L2 2 3 150U
C1 3 0 33U
LA 2 2A {10^LOGL}
CA 2A 2B {10^LOGC}
RA 2B 3 {10^LOGR}
.AC DEC 500 1E2 1E5
* Optimization Commands
.OPTIMIZE
    .PARAM LNOM={LOG10(150U)} LMIN={LOG10(150U)} LMAX={LOG10(1)}
.PARAMOPT LOGL=(LNOM,LMIN,LMAX)
    .PARAM CNOM={LOG10(10U)} CMIN={LOG10(1P)} CMAX={LOG10(1) }
.PARAMOPT LOGC=(CNOM,CMIN,CMAX)
    .PARAM RNOM={LOG10(10)} RMIN={LOG10(1E-3)} RMAX={LOG10(1E+6)}
    .PARAMOPT LOGR=(RNOM,RMIN,RMAX)
.OBJECTIVE AC LABEL=Q MAX(W('VM(3)'))
+ GOAL=MINIMIZE
```

This example represents a user-defined transformation based on the logarithmic function, such that:

$$
x=10^{\hat{x}}
$$

The exponent becomes the parameter to optimize. Consider the third . PARAMOPT command (on the previous page). The original formulation would be the following statements:

```
.PARAM RNOM=10 RMIN=1E-3 RMAX=1E+6
.PARAMOPT R=(RNOM, RMIN, RMAX)
```

In this case, the affine scaling transformation is not appropriate, because the upper bound RMAX $=10^{6}$ will dominate inside the expression of the matrix D:

$$
D=\frac{2}{R M A X-R M I N} \approx \frac{2}{R M A X}
$$

## Scaling of design objectives

It is also necessary to consider the scale of the design objectives. The scale of the design objectives matter in the stopping conditions and the computation of derivatives. Differing sizes among the component functions of an extracted measure F can cause the same types of problems as differing sizes among the optimization variables.

For instance, the algorithm requires a decrease in some merit function, and it is clear that if the units of two component functions of $\mathrm{F}(\mathrm{x})$ are widely different, then the smaller component function will be virtually ignored. For this reason, our algorithms also use a positive diagonal scaling matrix Df on the design objectives $\mathrm{F}(\mathrm{x})$, which works as D does on x . The diagonal matrix Df is chosen so that all the components of $\mathrm{Df} \mathrm{F}(\mathrm{x})$ will have about the same typical magnitude. In our interface, the user specifies Df initially by using the argument typval. The algorithm then sets:

$$
D f=\frac{1}{T Y P V A L}
$$

The result of this scaling procedure is described in the major output file .otm. The section in the .otm file begins with the heading Section 1- Scaling Transformation Design objectives. Please refer to "ASCII Output for Eldo Optimizer/SQP" on page 1191 for more information.

## Minimization and Maximization of Objectives

In order to simplify the presentation the case goal=minimize will be considered. The Eldo optimizer always minimizes, thus "maximizing $f(x)$ " is handled as "minimizing $-\mathrm{f}(\mathrm{x})$ ".

## Command syntax

The functions (or extracted measures) that the user wants to minimize have to be specified by complementing the . оbJective command as follows:

```
* Minimize or Maximize statements
.OBJECTIVE EXTRACT_INFO LABEL=f_m
+ {$MACRO|FUNCTION }
+ GOAL=MINIMIZE
+ [WEIGHT=MU_M]
```

The optional weight $\mu_{\mathrm{m}}$ is a positive number. By default, this number is initialized to one.

## Multiple specifications

This syntax allows multiple specifications of objective functions in the netlist. If several objectives are qualified as GOAL=minimize (or maximize), a weighted objective function will be built as the summation of all these particular measures. It means that the optimizer will minimize a unique objective that is the weighted sum of the whole objectives. Consider the following:

```
* Aggregation of two Minimize statements
.OBJECTIVE EXTRACT_INFO_1 LABEL=F_M_1
+ {$MACRO|FUNCTION }
+ GOAL=MINIMIZE WEIGHT=MU_M_1
.OBJECTIVE EXTRACT_INFO_2 LABEL=f_M_2
+ {$MACRO|FUNCTION}
+ GOAL=MINIMIZE WEIGHT=MU_M_2
```

These statements, where two design objectives have to be minimized, define a bi-criterion problem or a vector-valued objective function $\left(\mathrm{f}_{\mathrm{m}}{ }^{(1)}, \mathrm{f}_{\mathrm{m}}{ }^{(2)}\right)$. The technique used in this circumstance is a standard approach for finding solution of a vector optimization problem. This technique is named scalarization. Applied on our simple problem, it leads to the minimization of the global objective function:

$$
\mathrm{F}=\mu_{\mathrm{m}}{ }^{(1)} \mathrm{f}_{\mathrm{m}}{ }^{(1)}+\mu_{\mathrm{m}}{ }^{(2)} \mathrm{f}_{\mathrm{m}}{ }^{(2)}
$$

In other words, the optimization method considers a unique problem that is the aggregation of two concurrent problems.

In practice users have to experiment with the different choices of weights by successive adjustments. This technique is explained in "Role of the weight numbers" on page 1181.

## Effect of multiple sweeps and step increments

When multiple sweeps or multiple step increments on circuit parameters is present in the netlist, an extracted measure qualified as GOAL=MINIMIZE (or MAXIMIZE) must be considered as a multidimensional object. Consider the following statements where a number of P parameters have been specified:

```
* Design parameters specification
.STEP PARAM OMEGA_J <INCR_SPEC_OMEGA_J> ! for all j\in {1,\ldots,P}
* Minimize or Maximize statements
.OBJECTIVE EXTRACT_INFO LABEL=f_m
+ {$MACRO|FUNCTION}
+ GOAL=MINIMIZE
+ WEIGHT=MU_M
```

As above, the technique of scalarization is used, replacing the minimization of the vector-valued function by the minimization of the sum of the components of $f_{m}$. The optimizer will then form and minimize the function:

$$
F_{m}(x)=\mu_{m} \sum_{j(1), \ldots, j(P)} f_{m}\left(x ; \omega^{j(1)}, \ldots, \omega^{j(P)}\right)
$$

The extracted measure $\mathrm{f}_{\mathrm{m}}$ can be considered as a group of functions that has to be minimized.

## Note

With this kind of construct the weight number applies to all functions in the group. In other words, these functions have the same relative importance.

## Role of the weight numbers

The numbers $\mu_{\mathrm{m}}{ }^{(\mathrm{i})}$ are positive weight values attached to each design objective. For instance, the weight $\mu_{m}{ }^{(1)}$ can be thought of as quantifying the user's desire to make $\mathrm{f}_{\mathrm{m}}{ }^{(\mathrm{i})}(\mathrm{x})$ small. The user would take $\mu_{\mathrm{m}}{ }^{(\mathrm{i})}$ large if the user wants $\mathrm{f}_{\mathrm{m}}{ }^{(\mathrm{i})}(\mathrm{x})$ to be small. The ratio $\mu_{\mathrm{m}}{ }^{(\mathrm{i})} / \mu_{\mathrm{m}}{ }^{(\mathrm{j})}$ can be interpreted as the relative weight of the $i$ th objective compared to the $j$ th objective.

These remarks can help users that want to change the weights in order to get the lower values of a chosen objective, for example the $k$ th. To find an optimal point which trades off the $k$ th objective, users can increase the weight on the $k$ th objective.

## Goal Values for Objectives

A design objective that represents an equality specification for a performance measurement $f_{r}$ such that the extracted value of $f_{r}$ is as close as possible to a goal value $r$. This design objective can be defined with goal argument.

## Command syntax

The user can specify goal values for extracted measures by complementing the . овлестive command as follows:

```
* Goal values on measures
.OBJECTIVE EXTRACT_INFO LABEL=F_R
+ {$MACRO|FUNCTION}
+ GOAL=R
```

```
+ [WEIGHT=MU_R]
```

The optional weight $\mu_{\mathrm{r}}$ is a positive number. By default, this number is initialized to one. These functions are handled using the non-linear least squares approach, that is by minimizing the squared difference between the actual value of the measure $f_{r}$ and the goal value $r: \mu_{r}\left(f_{r}-r\right)^{2}$

## Multiple specifications

As previously stated, the extracted measures specified with GOAL=R are handled as the GOAL=MINIMIZE objectives, the following can be considered:

```
* Aggregation of two Minimize statements
.OBJECTIVE EXTRACT_INFO_1 LABEL=F_R_1
+ {$MACRO|FUNCTION}
+ GOAL=R_1 WEIGHT=MU_R_1
.OBJECTIVE EXTRACT_INFO_2 LABEL=F_R_2
+ {$MACRO|FUNCTION}
+ GOAL=R_2 WEIGHT=MU_R_2
```

This leads to the minimization of the global objective function:

$$
\mathrm{F}=\mu_{\mathrm{r}}^{(1)}\left(\mathrm{f}_{\mathrm{r}}^{(1)}-\mathrm{r}^{(1)}\right)^{2}+\mu_{\mathrm{r}}^{(2)}\left(\mathrm{f}_{\mathrm{r}}^{(2)}-\mathrm{r}^{(2)}\right)^{2}
$$

In practice users have to experiment with different choices of weights by successive adjustments (please refer to "Role of the weight numbers" on page 1181).

## Effect of multiple sweeps and step increments

The combination of optimization with goal values and multiple . STEP commands is supported. Consider the following statements where P parameters have been specified:

```
* Design parameters specification
.STEP PARAM OMEGA_1 <INCR_SPEC_OMEGA_1>
.STEP PARAM OMEGA_2 <INCR_SPEC_OMEGA_2>
.STEP PARAM OMEGA_P <INCR_SPEC_OMEGA_P>
* Goal statement
.OBJECTIVE EXTRACT_INFO LABEL=F_R
+ {$MACRO|FUNCTION }
+ GOAL=R
+ WEIGHT=MU_R
```

As above, the technique of scalarization is used, replacing the minimization of a vector-valued function by the minimization of the sum of the components of $f_{r}$. The optimizer will then form and minimize the function:

$$
F_{r}(x)=\mu_{r} \sum_{j(1), \ldots, j(P)}\left(f_{r}\left(x ; \omega^{j(1)}, \ldots, \omega^{j(P)}\right)-r\right)^{2}
$$

## Note

The weight number applies to all functions in the group, however, it is possible to associate a weight to each component of $f_{r}$. This can done with the .DATA command. Please refer to "Rules for explicit specification of simulation points" on page 1173 for more information.

## Range Constraints on Objectives

It is possible to specify bounds on design objectives. These objectives are named inequality constraints or range constraints. In this case the lower and upper bounds are equal $1=u$.

## Command syntax

Inequalities on measures correspond to relations like $1 \leq \mathrm{f}_{\mathrm{i}}(\mathrm{x}) \leq \mathrm{u}$ these constraints are specified by complementing the . овлестive command as follows:

```
* Range constraint
.OBJECTIVE EXTRACT_INFO LABEL=F_I
+ {$MACRO|FUNCTION}
+ LBOUND=L UBOUND=U
```

When the objective $f_{i}$ does not need to be bounded by a lower or an upper value, the arguments may be omitted. For example, if a design objective must be positive $f_{i} \geq 0$ (its lower bound is 0 ), the user can specify the following:

```
* Positive objective
.OBJECTIVE EXTRACT_INFO LABEL=F_I
+ {$MACRO|FUNCTION}
+ LBOUND=0.0
```

The Eldo optimizer/SQP algorithm handles them directly as "hard constraints". These objectives must be satisfied at the solution of the problem.

## Notes

Before examining the effect of multiple sweep commands on constraints, some notes are necessary:

- It is important to quote: the iterates (the successive values of design parameters taken during optimization) are by no means guaranteed to be feasible with respect to these constraints. If the optimization problem appears to be (hopefully) feasible, these will be satisfied at the solution, or in the vicinity of a solution.
- In general, the inequality constraints are more relevant than the equality constraints, because equalities may be difficult to satisfy. For instance, it is not possible to specify a tolerance associated to equality constraints. Consider the objective of fixing the Input Power Matching at a frequency of 2.4 GHz of a Low Noise Amplifier:

```
.EXTRACT AC LABEL=S11_dB@2.4GHz YVAL (SDB (1, 1), 2.4G)
+ GOAL=-15
```

It is obvious that a more appropriate objective would be to specify a target value with some additional tolerance, for example 1dB. The actual implementation of Eldo optimizer/SQP does not permit this feature. As a workaround, the user can combine GOAL objectives in order to center the design and range constraints with the same objective but on separate statements.

- As a consequence of the previous limitation, the equalities and inequalities are mutually exclusive. This means that the argument EQUAL cannot appear inside the same objective statement with the arguments lbound and ubound.
- Another type of condition that is not included in problem (P), is a constraint of the form $\mathrm{f}>0$. It is difficult to handle constraints of this form in an active set method such as the Eldo optimizer/SQP algorithm, because the feasible region is not closed and the constraint cannot be active at a solution. However, it can be useful to include them in the problem via the transformation $\mathrm{f}(\mathrm{x}) \geq \varepsilon>0$, possibly solving a sequence of problems in which $\varepsilon \rightarrow 0$ if the constraints happen to be active. The reason for doing this may be to prevent or dissuade $f(x)$ being evaluated at an infeasible point at which it is not defined.


## Multiple specifications

Multiple range constraints can be specified. For example, if the netlist consists of two statements such as:

```
* Aggregation of two range constraints
.OBJECTIVE EXTRACT_INFO_1 LABEL=F_I_1
+ {$MACRO|FUNCTION}
+ LBOUND=L_1 UBOUND=U_1
OBJECTIVE EXTRACT_INFO_2 LABEL=F_I_2
+ {$MACRO|FUNCTION}
+ LBOUND=L_2 UBOUND=U_2
```

These objectives will be optimized jointly, meaning that a vector of design variables x has to satisfy the system of inequalities:

$$
\binom{l^{(1)}}{l^{(2)}} \leq\binom{ f^{(1)}(x)}{f^{(2)}(x)} \leq\binom{ u^{(1)}}{u^{(2)}}
$$

This approach consists of defining a unique optimization problem that is the aggregation of all the constraint statements.

## Effect of multiple sweeps and step increments

As above, the combination of optimization with range constraints and multiple . STEP commands can be specified. Consider the following statements where P parameters have been specified:

```
* Design parameters specification
.STEP PARAM OMEGA_1 <INCR_SPEC_OMEGA_1>
.STEP PARAM OMEGA_2 <INCR_SPEC_OMEGA_2>
.STEP PARAM OMEGA_P <INCR_SPEC_OMEGA_P>
* Range cosntraint statement
.OBJECTIVE EXTRACT_INFO LABEL=f_i
+ {$MACRO|FUNCTION}
+ LBOUND=L
+ UBOUND=U
```

The optimizer will then form a group (or system) of inequalities as shown below:

$$
\forall j(1), \ldots, j(P),\left\{\begin{array}{c}
l\left(\omega^{j(1)}, \ldots, \omega^{j(P)}\right) \leq f_{i}\left(x ; \omega^{j(1)}, \ldots, \omega^{j(P)}\right) \\
f_{i}\left(x ; \omega^{j(1)}, \ldots, \omega^{j(P)}\right) \leq u\left(\omega^{j(1)}, \ldots, \omega^{j(P)}\right)
\end{array}\right.
$$

## The Optimization Methods

This section is concerned with the optimization command acting on the Eldo optimizer/SQP and the Eldo optimizer/Search algorithm parameters. In some specific cases, designers can perform optimization using the Eldo optimizer/Dichotomy, Secant and Passfail methods. Please refer to "Eldo Optimizer/Dichotomy/Secant/PassFail Arguments" on page 1140 to set-up a measurement with Eldo using this method.

## Eldo Optimizer/SQP Method

The Eldo optimizer/SQP optimizer is based on a Sequential Quadratic Programming method (SQP), using an active-set algorithm (proposed by Fletcher [2]) for solving large-scale quadratic programming problems. It is efficient for solving a large class of smooth optimization problems belonging to the following list:

- unconstrained and bound constrained problems (using only the statements GOAL=MINIMIZE $\mid$ MAXIMIZE and GOAL=RVALUE)
- systems of non-linear equations (using only the statement EQUAL=RVALUE)
- general (equality and inequality) constrained problems.

Users who wish to consult recent books giving a broader view of optimization techniques should refer to Nocedal and Wright [5], and Fletcher [3]. For more advanced books one may consult Bonnans, Gilbert, Lemarechal and Sagastizabal [1] and Gill, Murray and Wright [4].

Before continuing our presentation, some useful definition and mathematical notations are given. The design variables are denoted by:

$$
\mathrm{x}=\left(\mathrm{x}^{(1)}, \mathrm{x}^{(2)}, \ldots, \mathrm{x}^{(\mathrm{N})}\right)
$$

a vector of real numbers of dimension $N$. Therefore the space of variables is denoted by $\Re^{\mathrm{N}}$. The scalar product is denoted by:

$$
\langle u \mid v\rangle=\sum_{i} u^{(i)} v^{(i)} \text { onto the space } \Re^{\mathrm{N}} \text {, and its associated norm is }\|\mathrm{u}\| \text {. }
$$

A simplified structure of the $k$ th iteration can be depicted as:

- Step Computation: determine a direction of search $\mathrm{s}_{\mathrm{k}}$ (by solving a tangent quadratic subproblem $(\mathrm{QP})_{\mathrm{k}}$,)
- Step Assessment: find $\alpha_{\mathrm{k}}>0$ in order to minimize a chosen merit function $\mathrm{x} \rightarrow \Phi(\mathrm{x})$ along the line $\alpha \rightarrow \mathrm{x}_{\mathrm{k}}+\alpha \mathrm{s}_{\mathrm{k}}$,
- Update: $\mathrm{x}_{\mathrm{k}+1}=\mathrm{x}_{\mathrm{k}}+\alpha_{\mathrm{k}} \mathrm{s}_{\mathrm{k}}$.

This approach is referred to as a descent method since the search direction $\mathrm{s}_{\mathrm{k}}$ satisfies a descent property:

$$
\left\langle\mathrm{s}_{\mathrm{k}} \mid \nabla \Phi_{\mathrm{k}}\right\rangle<0
$$

where the vector $\nabla \Phi_{\mathrm{k}}$ represents the gradient of the chosen merit function. The role of the line search algorithm is to dampen the displacement $\mathrm{s}_{\mathrm{k}}$. Note that during the optimization process simulations are required at two distinct stages:

- the computation of derivatives of the extracted measures involved in the problem statement,
- the step assessment procedure, or line search algorithm


## Role of tolerances in Eldo optimizer/SQP

This section gives some indications on the role of the arguments tol_Grad, tol_feas, and TOL_OPT.

Suppose a value of $x$ that is a local minimizer of $f(x)$ in the interval $a \leq x \leq b$ is to be obtained:

| Minimize | $f(x)$ |
| :--- | :--- |
| Subject to | $a \leq x \leq b$ |

or using a SPICE formulation:
.OPTIMIZE

* Minimize Statement

```
.OBJECTIVE EXTRACT_INFO LABEL=F
+ {$MACRO|FUNCTION}
+ GOAL=MINIMIZE
* Design variable specification
.PARAMOPT X=(X0, A, B)
```

The optimality conditions OPTIM(x) in the definition of the TOL_GRAD argument are:

$$
\begin{array}{ll} 
& \mathrm{f}^{\prime}(\mathrm{x}) \text { if } \mathrm{a}<\mathrm{x}<\mathrm{b} \\
\operatorname{OPTIM}(\mathrm{x}) & \min \left(\mathrm{f}^{\prime}(\mathrm{x}), 0\right) \text { if } \mathrm{x}=\mathrm{a} \\
& \max \left(\mathrm{f}^{\prime}(\mathrm{x}), 0\right) \text { if } \mathrm{x}=\mathrm{b}
\end{array}
$$

Consider the first case in Figure 18-11. The minimum is the point $\mathrm{x}=\mathrm{b}$. The blue vector represents the derivative $f^{\prime}(x)$ at point $b$ (this is the opposite of the steepest descent direction $-f^{\prime}(x)$ at point $\left.b\right)$. The derivative $f^{\prime}(x)$ is negative, then is the number $\max \left(f^{\prime}(x), 0\right)=0$. When OPTIM(x) is zero or very small this indicates that the point $x$ is an optimum. The number tOL_GRAD is used in the stopping test of the Eldo optimizer/SQP. The point $x$ is optimal when the absolute value of $\operatorname{OPTIM}(\mathrm{x})$ is less than tol_Grad.

Consider the second case in Figure 18-11. Point $y$ is an unconstrained minimizer of $f$, since it lies strictly in the interval $[a, b]$. The optimality condition is then $\operatorname{OPTIM}(y)=f^{\prime}(y)$ which is the slope of $f$ at point $y$. OPTIM(y) equals zero. Note that the previous definition of the optimality conditions are related only to bound constrained minimization problems. The conditions OPTIM(x) are extended to the more general problems that the Eldo optimizer/SQP can treat.

In many cases the function values will be the result of extensive computation, possibly involving an iterative procedure that can provide rather few digits of precision at reasonable cost.

Figure 18-11. Illustration of the optimality conditions



For instance, suppose that a constraint function $\mathrm{c}^{(\mathrm{i})}(\mathrm{x})$ is computed for some relevant $x$ and if the first six digits are known to be correct. A constraint should be considered as active at its upper bound (or lower bound), if the magnitude of the difference between the values $c^{(i)}(x)$ and $c_{u}{ }^{(i)}$ (or cla ${ }^{(i)}$ respectively) is less than some tolerance of order $1.0 \times 10^{-6}$.

This tolerance, $\delta$, specifies how accurately the constraints should be satisfied. It defines the maximum absolute violation in non-linear constraints at a feasible point.

A constraint is considered satisfied if its violation does not exceed the tolerance $\delta$.
The feasible region for the constraints $\mathrm{c}_{1}{ }^{(\mathrm{i})} \leq \mathrm{c}_{\mathrm{I}}{ }^{(\mathrm{i})}(\mathrm{x}) \leq \mathrm{c}_{\mathrm{u}}{ }^{(\mathrm{i})}$ is shown in Figure 18-12.
Figure 18-12. Illustration of the constraints $\mathbf{c}^{\left({ }^{(i)}\right.} \leq \mathbf{c}^{(\mathrm{i})}(\mathbf{x}) \leq \mathbf{c u}^{(\mathrm{i})}$


The constraints are considered satisfied if $\mathrm{c}^{(\mathrm{i})}(\mathrm{x})$ lies in the region 2,3 , or 4 , and inactive if $\mathrm{c}^{(\mathrm{i})}(\mathrm{x})$ lies in region 3 . The constraint $\mathrm{c}_{1}{ }^{(\mathrm{i})} \leq \mathrm{c}^{(\mathrm{i})}(\mathrm{x})$ is considered active in region 2, and violated in region 1. Similarly, $c^{(i)}(x) \leq c_{u}{ }^{(i)}$ is active in region 4, and violated in region 5. For equality constraints $\mathrm{c}_{1}{ }^{(\mathrm{i})}=\mathrm{c}_{\mathrm{u}}{ }^{(\mathrm{i})}$, regions 2 and 4 are the same, and region 3 is empty. The default value is appropriate when the constraints contain data about the accuracy.

Note that specifying an appropriate tolerance on feasibility tol_feas may lead to several savings, by allowing the optimization procedure to terminate when the difference between function values along the search direction becomes as small as the absolute error in the values.

## Computation of finite-difference derivatives

One of the most demanding phase in terms of simulation is the computation of derivatives. The finite differences in the Eldo optimizer are used. Finite differencing is an approach to calculate the approximate derivatives whose motivation comes from Taylor's theorem. Like many software packages, the Eldo optimizer performs automatic calculation of finite differences whenever the simulator is unable (or unwilling) to supply the code to compute exact derivatives.

A popular formula for approximating the partial derivative $\partial \mathrm{F} / \partial \mathrm{x}$ at a given point is the forward differences or one-sided differences. The parameter denoted by $\mathrm{h}_{\mathrm{f}}$ is used, this controls the interval used to estimate the gradients of the function F by forward differences:

$$
\frac{\partial F}{\partial x} \approx \frac{F\left(x+h_{f}\right)-F(x)}{h_{f}}
$$

One-sided difference estimates are used to ensure feasibility with respect to an upper or lower bound on $x$. If $x$ is close to an upper bound, the trial intervals will be negative. The final interval is always positive.

- An approximation to the derivative of F can be obtained by evaluating the function F at $\mathrm{N}+1$ points and performing some elementary arithmetic.
- The resulting gradient estimates should be accurate to $\mathrm{O}\left(\mathrm{h}_{\mathrm{f}}\right)$ unless the functions are badly scaled.


## Eldo Optimizer/Search Method

The AMS 2006.1 release contains a new method of optimization that complete the previous ones. This method is named Search and is a combination of bisection and inverse quadratic interpolation. It is specified with the command .optimize method=Search. It allows minimization in the case of one dimensional problems. The Search method belongs to the class of derivative free optimization (DFO) algorithms.

The Search method has been introduced for completing the Dichotomy and Secant methods. It is also dedicated for solving problems having one variable and one extracted measure problems. This approach will run faster than the Dichotomy method and would be more robust than the modified Dichotomy (the Eldo optimizer/Secant).

The Search method is based on two distinct algorithms: find_zero and find_minimum. The algorithm FIND_ZERO aims to find a solution to:

Find $x$ such that $F(x)=0 \quad$ where $a \leq x \leq b$
or using a SPICE formulation:

```
.OPTIMIZE METHOD=SEARCH
```

* Design variable specification
. PARAMOPT $\mathrm{X}=(\mathrm{XO}, \mathrm{A}, \mathrm{B})$
* Goal value
. OBJECTIVE <ANALYSIS> LABEL=F_R <FUNCTION> GOAL=R

Note
Specifying a weight number with weight $=\mu_{\mathrm{r}}$ is allowed, however, it will not be considered. A warning message will be generated in this very specific case.

The most important feature of the method search can be stated in the following form:

- when the interval $[a, b]$ is not specified, the guess point $x 0$ is mandatory. One must have the command: . PARAMOPT $x=(x 0, *, *)$. The method search enters a search phase for finding an interval locating a solution.
- When the interval $[\mathrm{a}, \mathrm{b}]$ is specified, the method will start directly the search for a solution. The guess point is not used.
$\mathrm{F}(\mathrm{x})=\mathrm{f}_{\mathrm{r}}(\mathrm{x})-\mathrm{r}$ defines the difference between the actual measure $\mathrm{f}_{\mathrm{r}}$ and the goal value r . The FIND_ZERO algorithm uses a combination of bisection, secant, and inverse quadratic interpolation methods. The FIND_ZERO algorithm defines a zero as a point where the function crosses the x -axis. Points where the function touches but does not cross (see Figure 18-13), the $x$-axis are not valid zeros. For example, $F(x)=x^{2}$ is a parabola that touches the $x$-axis at $(0,0)$. Since the function never crosses the $x$-axis, no zero is found. For functions with no valid zeros, FIND_zERO executes until an undefined value is detected.

Figure 18-13. Non-valid and valid zeros


The algorithm FInd_MINIMUM attempts to return a value of $x$ that is a local minimizer of $F(x)$ in the interval $\mathrm{a} \leq \mathrm{x} \leq \mathrm{b}$ :

| Minimize | $F(x)$ |
| :--- | :--- |
| Subject to | $a \leq x \leq b$ |

The algorithm is based on the golden section search and parabolic interpolation techniques.

## Exploiting Output Results

After the optimization algorithm has been applied, the designer must be able to recognize whether it has succeeded in its task of finding a solution. This can be accomplished by analyzing the results of the optimization.

## Binary Output

```
.PLOT OPT WOPT(label_name) [(LOW, HIGH)] [(VERSUS)]
+ {OVN [(LOW, HIGH)]} [(SCATTERED)]
```


## Parameters

- OPT

Optimization analysis. The waves produced by this analysis can only be specified using the keyword wopt.

- WOPT

Only available for extracting waves generated during an optimization process. These are implicitly declared waves which have the same name as the extract label they refer to. They represent extract results versus the index of the run.

It is possible to plot extracted waves generated during an optimization process. These are implicitly declared waves which have the same name as the extract label they refer to. They represent extract results versus index of the run.

## Example

```
. EXTRACT tran label=FOO yval(v(node), 3n) !Define the extract
.PLOT OPT WOPT(FOO)
```


## ASCII Output for Eldo Optimizer/SQP

Starting Eldo v6.7, the ASCII output were defined as follows:

- the standard output controlled by Eldo is dedicated to simplified information on the optimization process.
- the optimization file .otm is organized in three major sections: initialization (scaling of variables and objectives), optimization phase, and the results of the process (final variables and objectives).

The following example will be considered. It is a slight modification of the LNA example (consult "Designing a Low Noise Amplifier (LNA)" on page 1149). The modified commands are shown below:

* Input Power Matching at Frequencies 2.4 GHz and 2.5 GHz
.EXTRACT AC LABEL=S11_dB@2.4GHz YVAL (SDB(1,1),2.4G) LBOUND=-15 UBOUND=-10
.EXTRACT AC LABEL=S11_dB@2.5GHz $\operatorname{YVAL}(\operatorname{SDB}(1,1), 2.5 G) \quad$ LBOUND $=-15$ UBOUND $=-10$
where the GOAL objective is replaced with two range constraints.


## Standard output

The standard output only involves the major phase of the optimization process. For each iteration Eldo will print a line of data. This line gives the cumulative number of simulations, and some algorithmic informations on the progress of optimization:

- Iter: major iteration number.
- Simul: cumulative number of simulations performed at the current iteration.
- LS Step: The step length $\alpha_{k}$ taken the direction $s_{k}$ at the $k$-th iteration. This step length is used to update the current iterate with the formula: $\mathrm{x}_{\mathrm{k}+1}=\mathrm{x}_{\mathrm{k}}+\alpha_{\mathrm{k}} \mathrm{s}_{\mathrm{k}}$

When the problem is well defined, this number should tend to 1.0 at the end of optimization. Failure of optimization can be detected with repetitive small steps.

- Merit Function: value of the merit function. This number will decrease as the solution is approached.
- Feas, Optim: these positive numbers are FEAS(x) and OPTIM(x) respectively. Both of these should be small in the vicinity of an optimal point.
- Slack: represents the norm of the slack variables added to the range constraints in order to prevent a potential inconsistency.

The following output has been obtained after running Eldo on the LNA example on the previous page:

```
Optimization Phase
    ==================
==> Detailed results in the major output file .otm
==> Output in the following order :
    Iter ... Major iteration number
    Simul ... Cumulative number of simulations
    LS Step ... Steplength parameter in linesearch
    Merit F ... Value of the merit function
    Feas ... Constraint violation (measure of feasibility)
    Optim ... Optimality criterion
    Slack ... Norm of variables to prevent inconsistency
==> Starting Optimization...
        9.1491101e+01 3.1e+00 2.0e+00 0.0e+00
        3 31 3.5e-01 5.8178533e+01 2.9e+00 2.0e+00 0.0e+00
        4 41 1.7e-01 3.8139395e+01 1.0e+00 2.0e+00 0.0e+00
        5 51 3.4e-01 1.3713556e+01 7.3e-01 2.0e+00 0.0e+00
```

```
Iter Simul LS Step Merit Function Feas Optim Slack
    81 797 1.0e+00 4.3858634e+00 0.0e+00 1.4e-03 0.0e+00
    82 808 1.0e-00 4.3858634e+00 0.0e+00 1.4e-04 0.0e+00
==> Optimization Results
==> Number Of Iterations 82
    Number Of Simulations 815
    Merit Function 4.3858634e+00
    Optimality 3.71e-06
    Feasibility 4.71e-11
==> Final Diagnostics: status code is 0
    The optimization seems to be successful.
    The required accuracy has been achieved.
    Final running mode: normal
==> End Of Optimization.
```

Small values of the optimality and feasibility numbers indicate that an optimum has been found. A more detailed analysis can be performed using the results printed in the .otm file.

## The .otm file and the viewotm script

The optimization file is a structured text file that is separated into sections and subsections. It uses a technique known as folding, which allows the user to filter out one or more sections in the .otm file, providing an overview of the results. Like a piece of paper which is folded to make it shorter. The advantage of folding is that the user can get a better overview of the structure of text, by folding lines of a section and omitting it. This technique is based on a similar feature available in the text editor vim.

The .otm file is then formatted for that purpose. The user has to run the service routine named viewotm on the .otm file in order to display the results. This routine can be invoked as follows:
viewotm [-l d] -f file.otm

-     - $\quad$ d

Where $d$ is the level of detail that users wants to view. The range of levels are 1 to 5 , level 1 (default) gives the least amount of data while level 5 gives the most amount of data.

- Level 1: only the results of the optimization are printed (merit function, values of the variables, and the objectives)
- Level 2: some additional informations related to the initialization phase are printed.
- Level 3, 4, or 5 the results and data is more detailed.

When an outer loop has been performed, the amount of data can be very large. In this case level 1 only reports simplified results in a table printed at the end of the .otm file. An example is given in "Additional experiments" on page 1153.

- -f

Name of the .otm file to be formatted.
For example, typing only: viewotm -f lnaopt.otm for the LNA problem will give the following output which are the final results (some very long lines were truncated to fit the width of the page). The sections concerning the scaling of variables and objectives can be viewed at higher level of details.

```
Optimization Results
=====================
    Section 1 - Statistics and Diagnostics
    ==> Number Of Iterations 83
    Number Of Simulations 838
    Merit Function 4.3858634e+00
    Optimality 2.01e-05
    Feasibility 1.49e-09
==> Final Diagnostics: status code is 0
    The optimization seems to be successful.
    The required accuracy has been achieved.
==> Final running mode: normal
==> Global elapsed time: 47 seconds
Section 2 - Status Of Variables
\begin{tabular}{llllll} 
Name & Status & Init Value & Final Value & Lower Bound \(\ldots\) \\
& & & & & \\
LS & UPR & \(2.5000 \mathrm{e}-10\) & \(3.0000 \mathrm{e}-09\) & \(0.0000 \mathrm{e}+00\) & \(\ldots\) \\
CPIN1 & LWR & \(1.0000 \mathrm{e}-13\) & \(0.0000 \mathrm{e}+00\) & \(0.0000 \mathrm{e}+00\) & \(\ldots\) \\
CPIN2 & BND & \(1.0000 \mathrm{e}-13\) & \(2.2340 \mathrm{e}-13\) & \(0.0000 \mathrm{e}+00\) & \(\ldots\) \\
CSIN & LWR & \(1.0000 \mathrm{e}-12\) & \(1.0000 \mathrm{e}-12\) & \(1.0000 \mathrm{e}-12\) & \(\ldots\) \\
LSIN & BND & \(1.0000 \mathrm{e}-10\) & \(1.0582 \mathrm{e}-08\) & \(0.0000 \mathrm{e}+00\) & \(\ldots\) \\
N1 & BND & \(3.0000 \mathrm{e}+01\) & \(1.9099 \mathrm{e}+01\) & \(1.0000 \mathrm{e}+01\) & \(\ldots\)
\end{tabular}
```

[^11]```
===============
```

```
==> Results of Last Simulation
*** Goal/Equal Objectives in simulator id(O)
    Name Init Value Curr Value Goal Value Weight
    AV_DB@2.4GHZ 1.1922e+01 2.0100e+01 2.0000e+01 1.0e+00
    AV_DB@2.5GHZ 1.1734e+01 2.0128e+01 2.0000e+01 1.0e+00
*** Inequality Constraints in simulator id(0)
    Name Type Feas Init Value Curr Value Lower Bnd
    S11_DB@2.4GHZ Range <.> -8.2277e-01 -1.4164e+01 -1.5000e+01
    S11_DB@2.5GHZ Range <.> -8.7893e-01 -1.5000e+01 -1.5000e+01
*** Minimize/Maximize Objectives in simulator id(0)
    Name Init Value Curr Value Weight Rel Chg %
    NF_DB@2.4GHZ 3.0310e+00 1.0860e+00 1.0e+00 -64.2
    NF_DB@2.5GHZ 3.0631e+00 1.1232e+00 1.0e+00 -63.3
    NFMIN_DB@2.4GHZ 1.0165e+00 1.0517e+00 1.0e+00 3.5
    NFMIN_DB@2.5GHZ 1.0640e+00 1.1118e+00 1.0e+00 4.5
==> End Of Optimization
```

When one outer loop is performed, the lowest level of details is represented by a table of results such as follows. There is one line for each optimization run.


## How to monitor the design objectives (MONIT_VAL options)

The information in the .otm file can be enriched. Some additional columns labelled with the name of a design objective can be printed during the optimization process. Note that when a design objective is represented by a single value, we will print this value as a "raw number".

The purpose of this feature is to allow you to monitor the optimization process. Consider the following case:

| Iter | Simul LS Step | Merit Function | Feas | Optim | Slack | FIT_IDRAIN |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | 10 | $1.0 \mathrm{e}+00$ | $2.6318512 \mathrm{e}+01$ | $0.0 \mathrm{e}+00$ |  | $0.0 \mathrm{e}+00$ | $4.1230176 \mathrm{e}-01$ |
| 2 | 20 | $1.0 \mathrm{e}+00$ | $2.5609867 \mathrm{e}+01$ | $0.0 \mathrm{e}+00$ | $2.0 \mathrm{e}+00$ | $0.0 \mathrm{e}+00$ | $3.7050156 \mathrm{e}-02$ |
| 3 | 39 | $3.0 \mathrm{e}+00$ | $1.6093292 \mathrm{e}-01$ | $0.0 \mathrm{e}+00$ | $2.0 \mathrm{e}+00$ | $0.0 \mathrm{e}+00$ | $2.9060346 \mathrm{e}-02$ |
| 4 | 51 | $3.5 \mathrm{e}-02$ | $1.6059068 \mathrm{e}-01$ | $0.0 \mathrm{e}+00$ | $6.3 \mathrm{e}-01$ | $0.0 \mathrm{e}+00$ | $2.7052106 \mathrm{e}-02$ |
| 5 | 63 | $2.1 \mathrm{e}+01$ | $8.4372205 \mathrm{e}-02$ | $0.0 \mathrm{e}+00$ | $5.4 \mathrm{e}-01$ | $0.0 \mathrm{e}+00$ | $2.7050156 \mathrm{e}-02$ |
| 6 | 73 | $1.0 \mathrm{e}+00$ | $8.0979363 \mathrm{e}-02$ | $0.0 \mathrm{e}+00$ | $8.1 \mathrm{e}-01$ | $0.0 \mathrm{e}+00$ | $2.7050007 \mathrm{e}-02$ |
| 7 | 85 | $2.6 \mathrm{e}+01$ | $6.8441845 \mathrm{e}-02$ | $0.0 \mathrm{e}+00$ | $1.8 \mathrm{e}-01$ | $0.0 \mathrm{e}+00$ | $2.7050000 \mathrm{e}-02$ |

The associated optimization statement could be:

```
.OBJECTIVE DC LABEL=FIT_IDRAIN I(V101)
+ GOAL=DATA_D25X25(IDS) TYPVAL=1E-4 MONIT_VAL=ERRMEAN
```

Usually we do not print each error function as only the global error function, also known as RMS function, is needed. This is the sum of the squared residuals:

$$
\frac{1}{N_{r}} \sum_{k}\left(f_{r}^{(k)}(x)-r^{(k)}\right)^{2}
$$

where: $r^{(\mathrm{k})}$ is the goal value associated to the $k$ th error function, and $\mathrm{N}_{\mathrm{r}}$ the number of error functions.

We can also print the maximum or the minimum value for the whole set of values

$$
\left\{f_{r}^{(1)}(x), \ldots, f_{r}^{\left(N_{r}\right)}(x)\right\}
$$

These options are explained in the following list:

- MONIT_VAL=MEAN, the printed value will be the sum $\frac{1}{N_{r}} \sum_{k} f_{r}^{(k)}(x)$ (which is the
mean value of the functions $\left.f_{r}^{(k)}(x)\right)$,
- MONIT_VAL=MAX or MONIT_VAL=MIN, the printed value will be the maximum $\operatorname{Max}\left\{f_{r}{ }^{(k)}(x)\right\}$ or the minimum $\operatorname{Min}\left\{f_{r}{ }^{(k)}(x)\right\}$,
- MONIT_VAL=ERRMEAN, the printed value will be the sum $\frac{1}{N_{r}} \sum_{k}\left(f_{r}^{(k)}(x)-r^{(k)}\right)^{2}$ of
the squared residuals,
- MONIT_VAL=ERRMAX or MONIT_VAL=ERRMIN, the printed value will be the maximal error function $\operatorname{Max}\left\{\left|f_{r}^{(k)}(x)-r^{(k)}\right|\right\}$ or the minimal error function $\operatorname{Min}\left\{\left|f_{r}{ }^{(k)}(x)-r^{(k)}\right|\right\}$.

When the design objectives are specified as minimize and maximize the situation is similar, but there is no notion of "error function" associated to these objects. One can consider the following netlist as a basic example:

```
* Design parameter (temperature)
.STEP TEMP -25 150 5
* Design variable specification
.PARAMOPT
+ x = (x0,a,b)
* Minimization
.OBJECTIVE
+ EXTRACT_INFO LABEL=f_m
+ {$MACRO|FUNCTION}
+ GOAL=MINIMIZE
+ PRN_VAL=ERRMEAN
```

This will minimize the functions $\mathrm{f}_{\mathrm{m}}\left(\mathrm{x} ; \mathrm{T}_{\mathrm{k}}\right)$ with respect to x subject to the constraints $\mathrm{a} \leq \mathrm{x} \leq \mathrm{b}$, where $T_{k}$ represents a point of discretization in the temperature interval [-25, 150]. It could be useful to monitor the mean value or the max/min values of these objectives. These options are addressed in the following list:

- MONIT_VAL=MEAN, the printed value will be the sum $\frac{1}{N_{m}} \sum_{k} f_{m}{ }^{(k)}(x)$,
- MONIT_VAL=MAX or MONIT_VAL=MIN, the printed value will be the maximal value $\operatorname{Max}\left\{f_{m}{ }^{(k)}(x)\right\}$ or the minimal value $\operatorname{Min}\left\{f_{m}{ }^{(k)}(x)\right\}$.

We now consider the case of inequality constraints. The notion of "error functions" can be extended to this case, we call these functions the violation associated to a constraint. We will consider a group of range constraints:

$$
l^{(k)} \leq f_{i}^{(k)}(x) \leq u^{(k)}
$$

the maximum violations $\mathrm{v}_{\mathrm{u}}$ and $\mathrm{v}_{\mathrm{l}}$ are defined as follows:

$$
v_{u}^{(k)}=\max \left\{0, f_{i}^{(k)}(x)-u^{(k)}\right\}
$$

and

$$
v_{l}^{(k)}=\max \left\{0, l-f_{i}^{(k)}(x)\right\}
$$

These numbers are always positive $\mathrm{v}_{1, \mathrm{u}} \geq 0$. This is summarized in the following list:

- MONIT_VAL=MEAN, the printed value will be the sum $\frac{1}{N_{i}} \sum_{k} f_{i}^{(k)}(x)$,
- MONIT_VAL=MAX or MONIT_VAL=MIN, the printed value will be the maximal value $\operatorname{Max}\left\{f_{i}{ }^{(k)}(x)\right\}$ or the minimal value $\operatorname{Min}\left\{f_{i}^{(k)}(x)\right\}$,
- MONIT_VAL=ERRMEAN, the printed value will be the mean value of the constraint violations $\frac{1}{N_{i}} \sum_{k}\left(v_{l}^{(k)}+v_{u}^{(k)}\right)$,
- MONIT_VAL=ERRMAX or MONIT_VAL=ERRMIN, the printed value will be the maximal constraint violation $\operatorname{Max}_{k}\left\{v_{l}^{(k)}+v_{u}^{(k)}\right\}$ or the minimal constraint violation $\operatorname{Min}_{k}\left\{v_{l}^{(k)}+v_{u}^{(k)}\right\}$.


## Final diagnostic conditions

When the optimizer has finished, a status code is printed in the Optimization Results. It is essential to check that the value of the return code (and its associated message) and the effective results of optimization (design variables and objectives). The final diagnostics only indicate the final status of the optimizer before it exits. These messages and their meaning are described in Table 18-11:

Table 18-11. Optimization Result Status Code

| Code | Message and meaning |
| :--- | :--- |
| 0 | The optimization seems to be successful. The required accuracy has <br> been achieved. <br> The iterates have converged to a point $\bar{x}$ that satisfies the optimality conditions to <br> the accuracy requested by the optional parameters roL_OPT or toi_GRAD and <br> toL_FEAS (please refer to "The Optimization Methods" on page 1185). The user <br> should verify whether the following two conditions have been satisfied: <br> o The final value of optimality is significantly small. <br> o The final values of Feasibility is significantly small. Note, these <br> values are set to zero if there are no equality or inequality <br> constraints. |
| 1 | Optimization was not successful. The maximum number of simulation <br> runs has been reached. <br> The limiting number of iterations, determined by the optional parameter |
| MAX_ITER has been reached. <br> Check the iteration log contained in the .otm file. If the optimizer appears to be <br> making progress, MAX_ITER may be too small. If so, increase its value and rerun <br> the optimizer, possibly using the values of the design variables obtained so far <br> (this can be considered as a warm start). |  |

Table 18-11. Optimization Result Status Code

| Code | Message and meaning |
| :--- | :--- |
| 2 | The current point cannot be improved. A sufficient decrease in the <br> merit function could not be attained during the last line search. <br> This may occur because the user has requested an overly stringent <br> accuracy. <br> A sufficient decrease in the merit function could not be attained during the final <br> line search. This sometimes occurs because an overly stringent accuracy has been <br> requested, i.e. TOL_OPT is too small. In this case the user should verify the two <br> conditions described under Code = 0 to determine whether or not the final <br> solution is acceptable. It may happen that an additional status code is raised. This <br> status can only take the values: Code= 0, Code=6, or Code=11. |
| 4 | Optimization was not successful. The maximum number of simulation <br> runs has been reached. <br> The limiting number of simulations, determined by the optional parameter |
| MAx_sIMUL has been reached. |  |$|$| The current point is feasible and quite optimal, however, the |
| :--- |
| required accuracy has not been achieved. The optimizer is within |
| le-2 of satisfying the TOL_OPT (or TOL_GRAD) optimality tolerance. |
| The optimizer is within 1x10-2 of satisfying the ToL_OPT (or ToL_GRAD) |
| optimality tolerance. For next runs, the user should check that TOL_OPT is not too |
| small. |

Table 18-11. Optimization Result Status Code

| Code | Message and meaning |
| :--- | :--- |
| 10 | The current point cannot be improved. The Hessian matrix has been <br> reset too many times. It indicates that the line search failed to <br> find a sufficiently better point for a large number of iterations. <br> This message should appear very rarely. This is an algorithmic weakness of the <br> method implemented in the Eldo optimizer/SQP. Try to start the optimization <br> from a different point. |
| 11 | The starting point cannot be improved. It may happen that the <br> derivative are inaccurate or the starting point is already <br> critical. <br> Check that the objectives to optimize are well-defined at the starting point. |
| 12 | The current point cannot be improved. The last QP step was too <br> poor to allow a sufficient progress of the iterations. <br> This may indicate that the extracted measures and their derivatives have a low <br> precision at the current point. |
| 13 | Optimization was not successful. Either the objective function or <br> the constraints seem to be undefined at the starting point. The <br> optimization was abandoned. <br> The current version of the Eldo optimizer/SQP cannot treat problems where the |
| objectives returned by Eldo (at the first iterate) have the UNDEF value. Try to |  |
| eliminate such cases by using a two-stage approach. |  |

## Normal and elastic modes of termination

The SQP algorithm is able to make explicit allowance for infeasible constraints when computing the incremental steps obtained from a sequence of sub-problems. This phenomenon is referred to as local infeasibility.

In constrained optimization, a situation where no feasible solution exists can occur. In this case the constraints are inconsistent and the problem is infeasible. If all the constraints are bounds on the variables:

$$
\mathrm{x}_{\mathrm{l}}{ }^{(\mathrm{i})} \leq \mathrm{x}^{(\mathrm{i})} \leq \mathrm{x}_{\mathrm{u}}{ }^{(\mathrm{i})}
$$

It is simple to determine whether a feasible point exists, since the $i$ th is only inconsistent when:

$$
\mathrm{x}_{\mathrm{l}}{ }^{(\mathrm{i})}>\mathrm{x}_{\mathrm{u}}{ }^{(\mathrm{i})}
$$

Such infeasibilities are automatically trapped when parsing the .PARAMOPT command. Conversely, with general constraints there are no simple characteristics that identify whether a feasible solution exists.

## Figure 18-14. Illustration of the 'elastic' mode (1)



The following simple example illustrates the possible situation, see also the figure 18-14 for a graphical illustration. Consider the optimization problem with two variables X1 and X2

```
.PARAMOPT X1=(4, 0, *)
.PARAMOPT X2=(7, 0, *)
.OBJECTIVE DC LABEL=C (X1 + X2) UBOUND=-1
```

These statements define two bound constraints on the variables: $x_{1} \geq 0$ and $x_{2} \geq 0$, and the linear constraint $x_{1}+x_{2} \leq-1$. By considering the graphical representation, one may also see that they define two disjoint sets of points. The optimization problem is then infeasible.

In order to cope with this issue, the SQP optimizer can run in one of two different modes:

- normal mode
- elastic mode

The algorithm automatically enters the 'elastic' mode when a situation of infeasibility is detected. This mode performs a shift of the bounds on constraints. In our example, we can add a positive number $v \geq 0$ to the upper bound UBOUND:

$$
x_{1}+x_{2} \leq-1+v
$$

and try to minimize the value of $v$ or minimize the constraint violation. This numerical modification is graphically displayed in the right part of figure $18-14$, where the green colored
area represents the non empty feasible domain. It is clear that $v=1$ is the smallest of the violation such that there exist a feasible point.

For example, we solved this simple problem with the SQP optimizer. The .otm file gives the following results for the optimized variable:

| Name | Status | Init Value | Final Value | Lower Bound |
| :---: | :---: | :---: | :---: | :---: |
| X1 | BND | $4.0000 \mathrm{e}+00$ | $0.0000 \mathrm{e}+00$ | $0.0000 \mathrm{e}+00$ |
| X2 | BND | $7.0000 e+00$ | $0.0000 \mathrm{e}+00$ | $0.0000 \mathrm{e}+00$ |

where the final value of the parameters is $(0,0)$ the origin point. The final status of the constraint is given by

```
Section 3 - Status Of Objectives
-------------------------------------
    *** Inequality Constraints in simulator id(0)
\begin{tabular}{llrc} 
Type Name & Init Value & Opt Value & Violation \\
UPR & CONSTR1 & \(* * * 1.1000 \mathrm{e}+01\) & \(1.0000 \mathrm{e}-06\)
\end{tabular}
```

The optimal value (Opt Value) of the constraint is $1.0 \times 10^{-6}$ and the number in the last column (Violation) gives the violation or equivalently the value of the additional variable $v$. In this case, the violation is a strictly positive value 1.0.

Note that this approach has very interesting properties, for instance the optimal solution often violates only a small number of the constraints. Therefore, a point that satisfies many of the constraints has been computed, i.e. a large subset of constraints that are feasible have been identified. This is more informative for the user, than finding that the constraints are mutually feasible (this approach is closely related to the L1-norm regularization technique).

Consider the following problem with two variables. We want to minimize some function $f\left(x_{1}, x_{2}\right)$ subject to the constraint

$$
\left(x_{1}+1\right)^{2}+x_{2}^{2} \leq \frac{3}{4}
$$

which defines a disk centered at $(-1,0)$ with radius $\sqrt{3} / 2$, and the second constraint

$$
\left(x_{1}-1\right)^{2}+x_{2}^{2} \leq \frac{3}{4}
$$

which defines the symmetrical disk centered at $(1,0)$. This situation is displayed in figure 18-15.

## Figure 18-15. Illustration of the 'elastic' mode (2)



It is clear that there is no feasible solution. If we run the Eldo optimizer on this example:

```
.PARAMOPT X1=(-2, *, *)
.PARAMOPT X2=(-2, *, *)
```

```
.OBJECTIVE DC LABEL=CIRCLE1 ( (X1-1)**2 + X2**2 ) UBOUND=0.75
.OBJECTIVE DC LABEL=CIRCLE2 ( (X1+1)**2 + X2**2 ) UBOUND=0.75
```

we get the following output

| Iteration 0 |  | Feas $=1.2 \mathrm{e}+01$, |  | $6.0 \mathrm{e}+00$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Iter | Simul | LS Step | Merit Function | Feas | Optim | Slack |
| 1 | 10 | 1.0e+00 | $6.3505943 \mathrm{e}-01$ | $1.2 e+00$ | 6.0e-04 | $0.0 \mathrm{e}+00$ |
| 2 | 16 | $3.3 \mathrm{e}-01$ | $1.7787634 \mathrm{e}+00$ | $3.9 \mathrm{e}-01$ | $7.8 \mathrm{e}-01$ | $0.0 \mathrm{e}+00$ |
| 3 | 22 | 1.9e-01 | $4.3108310 \mathrm{e}+00$ | $2.9 \mathrm{e}-01$ | 9.0e-01 | $0.0 \mathrm{e}+00$ |
| 4 | 28 | $3.4 \mathrm{e}-02$ | $3.7393098 \mathrm{e}+01$ | $2.5 \mathrm{e}-01$ | $1.3 \mathrm{e}+00$ | $0.0 \mathrm{e}+00$ |
| 5 | 34 | $3.7 e-04$ | $6.5283185 \mathrm{e}+03$ | $2.5 \mathrm{e}-01$ | $1.9 \mathrm{e}+00$ | $0.0 \mathrm{e}+00$ |
| 6 | 40 | $1.0 \mathrm{e}-00$ | $1.5304677 \mathrm{e}+04$ | $2.5 \mathrm{e}-01$ | $2.0 \mathrm{e}+00$ | 3. 5 e+00 |
| 7 | 46 | $2.2 \mathrm{e}-01$ | $1.5238534 \mathrm{e}+04$ | $5.1 e-03$ | $7.7 e+03$ | 3. $6 \mathrm{e}-01$ |
| 8 | 53 | 1.3e-02 | $1.4929878 \mathrm{e}+04$ | $5.1 e-03$ | $7.5 e+03$ | 3.5e-01 |
| 9 | 61 | 9.9e-01 | $1.5000628 \mathrm{e}+04$ | $1.1 \mathrm{e}-02$ | $1.9 \mathrm{e}+03$ | 3.5e-01 |
| Iter | Simul | LS Step | Merit Function | Feas | Optim | Slack |
| 10 | 65 | $1.0 \mathrm{e}+00$ | $1.5000626 e+04$ | $4.1 \mathrm{e}-04$ | $2.8 e+01$ | 3.5e-01 |
| 11 | 69 | $1.0 \mathrm{e}+00$ | $1.5000625 e+04$ | $1.2 \mathrm{e}-07$ | $1.4 \mathrm{e}+01$ | 3.5e-01 |

The column Slack is the value of the global constraint violation, it is the norm of the artificial variables $\left(v_{1}, v_{2}\right)$ added to the upper bound UBOUND for each constraint. For instance the first constraint becomes

$$
\left(x_{1}+1\right)^{2}+x_{2}^{2} \leq \frac{3}{4}+v_{1}
$$

and similarly the second constraint becomes

$$
\left(x_{1}-1\right)^{2}+x_{2}^{2} \leq \frac{3}{4}+v_{2}
$$

The value Slack becomes strictly positive after the 6th iteration. This phenomenon can be interpret as follows:

- after the 6th iteration the algorithm detected that the problem is locally infeasible,
- two artificial variables are then introduced such that the constraints become consistent. Graphically, this can be interpreted as increasing the radius of the two circles such that they do intersect.
- The goal of the algorithm is then to find a solution point such that the constraint violation is minimized.

The final solution is given in the following output:

```
Section 2 - Status Of Variables
----------------------------------
    Name Status Init Value Final Value
    X1 FR -2.0000e+00 -5.0009e-07
    X2 FR -2.0000e+00 1.6166e-05
Section 3 - Status Of Objectives
---------------------------------
*** Inequality Constraints in simulator id(0)
\begin{tabular}{lllcc} 
Type Name & Init Value & Opt Value & Violation \\
UPR & CIRCLE1 & \(* * * 1.3000 e+01\) & \(1.0000 e+00\) & \(* * * 2.5000 e-01\)
\end{tabular}
UPR CIRCLE2 *** 5.0000e+00 1.0000e-00 *** 2.5000e-01
```

We can observe that the constraint violations have been minimized. The actual value of the violation is $v_{1}=1 / 4$ for the first constraint and $v_{2}=1 / 4$ for the second. The solution point is approximately the origin $(0,0)$. These remarks are consistent. The algorithm automatically increased the radius of each circle such that the feasible domain becomes a non empty set. The feasible set reduces to the singleton $(0,0)$.

## Final status of variables

The final value of the design variables are listed in the second section of the optimization results file (.otm). This section starts with the title: "Section 2 - Status Of Variables".

The output informations are the initial and final continuous value of the design parameters labeled with "Init Value" and "Final Value" respectively. The lower and upper bounds are also printed. The value labeled with "Discr Value" represents the final value after projection onto the grid of discretization (consult "Discretization of Design Variables" on page 1146 for details).

## Final status of objectives

The final value of the objectives are listed in the third section. This section starts with the title "Section 3- Status Of Objectives". The objectives are printed according to their category. The level of the output is controlled by the argument PRNVAL (see ".OBJECTIVE" on page 1134). The printed values are described below:

- When the design objective has the GOAL (and EQUAL) argument. The initial, the current and goal values are printed with the labels: "Init Value", "Opt Value" and "Goal Value" respectively. The value "Rel Chg" represents the relative change (defined in percentage) of the design objectives. The weight number is also printed (as a percentage).
- The MINIMIZE and MAXIMIZE objectives are printed with their initial and final value. The value "Rel Chg" represents the relative change of the objective.
- The inequality constraints (with LBOUND and UBOUND arguments) are printed with an additional status represented by a symbol " $* * *$ " if the constraint violation is non zero. This symbol is printed to indicate that the initial or the final objective are not satisfied.


## Last simulation with final solution

The results of optimization are compared to the final results obtained after discretization of the design variables. This section starts with the title "Analysis of Last Simulation". The objectives are printed according to their category. For example, the 'optimized value' of a MINIMIZE objective is labeled as "Opt Value" and the final value obtained after discretization is given in the column "Discr Value". It is then possible to observe a possible discrepancy due to the discretization algorithm.

## References

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5. J. Nocedal and S. W. Wright. Numerical Optimization. Springer Series in operations Research, Springer, New York, 1999.
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# Chapter 19 Monte Carlo Analysis 

## Introduction

Originally, the Computer Aided Design (CAD) tools have been used to study the nominal design of an integrated circuit (IC). Due to the disturbances of the IC manufacturing process, the effective performance of the mass produced chips are different than those for the nominal design. Process-related performance variations may lead to low manufacturing yield, and unacceptable product quality. For these reasons, statistical circuit design techniques are required to design the circuit parameters.

The purpose of the Monte Carlo (MC) analysis is to determine the uncertainty in estimates for dependent variables of interest. Thus MC analysis focuses on data, and how uncertainty in data propagates through computations. This definition of uncertainty involves model input and output models. In our context, the models of interest are provided by circuit simulations. For instance, Eldo takes a netlist describing the circuit transistors, resistors, capacitors, and so on, and their connections and translates this description into mathematical equations. The inputs are therefore the various design parameters, the process parameters and the environmental conditions. On the other side, the output space is characterized by the circuit performance of interest.

Monte Carlo-based uncertainty analysis is performed on multiple model evaluations with randomly selected model input variables, and then using the results of these evaluations to determine the uncertainty in model predictions, and the input variables that gave rise to this uncertainty. In general, a Monte Carlo analysis involves four steps:

- A range and distribution are selected for each input factor. These selections will be used in the next step in the generation of a sample from the input factors.
- A sample of points is generated from the distribution of the inputs specified in the first step. The result of this step is a sequence of sample elements.
- The circuit simulator is fed with the sample elements and a set of extracted measures is produced. In essence, these evaluations create a mapping from the space of the inputs to the space of the results. This mapping is the basis for subsequent uncertainty analysis.
- The results of model evaluations are used as the basis for the uncertainty analysis. For example, one way to characterize the uncertainty is with a mean value and a variance. Other output statistics are also provided.

The Monte Carlo-based approach has several advantages: it forces explicit acknowledgment of all sources of uncertainty, it can take account of any distribution and correlation and can be applied to complex simulations.

## Usage

## Define the .MC Command

The first step in Monte Carlo is to define the .mC command.

```
.MC RUNNO [OUTER] [OV] [SEED=integer_value] [NONOM] [ALL]
+ [VARY=LOT|DEV] [IRUN=val] [NBBINS=val] [ORDMCS] [MCLIMIT]
+ [PRINT_EXTRACT=NOMINAL|ALL|run_number] [SIGBIN=val]
+ [MAXABSBIN=val] [MAXRELBIN=val]
+ [MONITOR] [AUTOSTOP=expression]
+ [SAVE=mc_file] [RESTART=mc_file]
```

- RUNNO

Number of simulation runs (probability samples). Integer.

- outer

When there are both . Step and .mc commands, Eldo performs a full Monte Carlo analysis for each point of the . Step command. If the keyword outer is specified on the .MC command the nesting of the simulations will be inverted. Instead, a . step will be performed at each Monte Carlo run (the outer keyword must be placed after the specification of the number of Monte Carlo runs). .mC outer does not work with a variation in temperature with the .TEMP command (for example .TEMP $0 \quad 39$ 80) or . STEP TEMP command, but does work with a single temperature definition with .TEMP (for example .temp 70).

- ov

Compute the standard deviation of the quantity ov and output to the ASCII output file. The format of ov is one of:
$I(V x x[, V y y])$, which specifies the difference in current between voltage sources Vxx and Vyy. If Vyy and the comma are omitted, then this will return just the current through Vxx;
$\mathrm{V}(\mathrm{n} 1[, \mathrm{n} 2])$, which specifies the voltage potential between nodes n 1 and n 2 . If n 2 and the comma are omitted, then this will return the potential between node n 1 and ground.
Other analysis output formats are available for AC analysis. Please refer to ".PRINT" on page 830 .

- SEED=i

The integer $i$ is used to initialize the pseudo-random sequence of numbers for the probability distribution. Running Monte Carlo twice with the same seed value will give the same results.

- NONOM

Nominal run for Monte Carlo analysis is bypassed. This option is used by Accusim. When nonom is active, the all option of .mC is enabled as well.

## - ALL

When specified, the waveform results of every Monte Carlo simulation run are stored in the output files (one set per runno). Without this, only the nominal, minimum, and maximum results are saved. This includes both ASCII and binary wave results.

- $\quad$ IRUN=n
n is an integer. This runs only the nth Monte Carlo simulation of a series. For example:

```
.MC 10 IRUN=3
```

tells Eldo to run the third Monte Carlo analysis of the 10 point series. If IRUN $\leq 0$ it will be ignored and a warning generated.

This can also be used with simulation information that has been saved for a specific run (index) of a Monte Carlo analysis using the carlo argument of the . Save command. See ".SAVE" on page 857. This is useful for debugging purposes, as the DC value would be reinjected into the single Monte Carlo run specified.

- VARY=Lot|Dev

Determines whether Monte Carlo variations are independent or correlated for model Monte Carlo variables. When specifying DEv, then DEv and DEvx variation is taken into account. Only one vary specification can be set. By default, Eldo applies LOt, Dev and DEVx variation.

- nBBINS=VAL

Specifies the number of bins for the histogram produced when Monte Carlo analysis is used with .extract statements. The default is 10 .

- ORDMCS

Determines whether multiple Monte Carlo parameters in the simulation share the same pseudo-random probability values or not.
For example, without ordmcs, Eldo generates a single probability stream p1, p2, p3, ..., pn. Each probability is between 0 and 1 . These probability series are shared among the variables. For two Monte Carlo variables, A and B, the assignment is:

$$
\begin{aligned}
& \text { Run 1: } A=p 1, B=p 2 \\
& \text { Run 2: } A=p 3, B=p 4 \\
& \text { Run 3: } A=p 5, B=p 6 \\
& \text { Run } n: A=p[2 n-1], B=p[2 n]
\end{aligned}
$$

For four Monte Carlo variables, $\mathrm{A}, \mathrm{B}, \mathrm{C}$, and D , the assignment is:

$$
\begin{aligned}
& \text { Run 1: } A=p 1, B=p 2, C=p 3, D=p 4 \\
& \text { Run 2: } A=p 5, B=p 6, C=p 7, D=p 8 \\
& \text { Run 3: } A=p 9, B=p 10, C=p 11, D=p 12 \\
& \text { Run } n: A=p[4 n-3], B=[4 n-2], C=[4 n-1], D=[4 n]
\end{aligned}
$$

With ordmcs, each variable gets its own probability series. For two Monte Carlo variables, the assignment is:

Run 1: $\mathrm{A}=\mathrm{pa} 1, \mathrm{~B}=\mathrm{pb} 1$
Run 2: $\mathrm{A}=\mathrm{pa} 2, \mathrm{~B}=\mathrm{pb} 2$
Run 3: $A=p a 3, B=p b 3$
Run n: $\mathrm{A}=\mathrm{pa}[\mathrm{n}], \mathrm{B}=\mathrm{pb}[\mathrm{n}]$
For four Monte Carlo variables, the assignment is:
Run 1: $\mathrm{A}=\mathrm{pa} 1, \mathrm{~B}=\mathrm{pb} 1, \mathrm{C}=\mathrm{pc} 1, \mathrm{D}=\mathrm{pd} 1$
Run 2: $A=p a 2, B=p b 2, C=p c 2, D=p d 2$
Run 3: $A=p a 3, B=p b 3, C=p c 3, D=p d 3$
Run n : $\mathrm{A}=\mathrm{pa}[\mathrm{n}], \mathrm{B}=\mathrm{pb}[\mathrm{n}], \mathrm{C}=\mathrm{pc}[\mathrm{n}], \mathrm{D}=\mathrm{pd}[\mathrm{n}]$

- MCLImIT

Specifies that all parameters with statistical distribution (DEv, DEvx, or цот) will have their distribution modified to one of two deviation values. These values correspond to the maximum deviation of the original distribution as defined by the option SIGTAil. For example, a parameter with a nominal value of 1.0 , a statistical deviation of $\mathrm{DEV} / \mathrm{GAUSS}=5 \%$, and with option sigtail at its default value of 4 , the two values will be calculated as follows:

$$
1-(4 * 0.05)=0.8, \quad 1+(4 * 0.05)=1.2
$$

This functionality can be useful to force Monte Carlo runs to use maximum deviation combinations. MCLImIt affects all statistical parameters whatever their original distribution.

- PRINT_EXTRACT=NOMINAL $\mid$ ALL $\mid$ run_number

Specifies for which run extracted values should be printed and written to output files.

## NOMINAL

Only the nominal extracted value is printed (default).
ALL
Extracted values are printed for all runs.

```
run_number
```

Extracted values are printed only for the specified run_number ( 0 is the nominal run).

- SIGBIN=VAL

Can be specified to truncate the histogram to a certain number of sigmas. Eldo will gather all the samples above "mean + SIGBIN $\times$ sigma" in the Above bin, and all the samples below "mean-SIGBIN $\times$ sigma" in the Below bin. This might be useful when there are a few untypical samples that would otherwise corrupt the min and max of the histogram.

- MAXABSBIN=VAL

Can be specified to simplify the histograms printed out in the .chi file, if they are difficult to read if most of the samples are in the same bin. If there are more than MAXABSBIN terms in a bin, then that bin will be expanded recursively, and a new histogram will be printed out for that bin. This corresponds to a zoom in each of the bins which contain too much samples. Default value is -1 , i.e. this option is not active by default.

- MAXRELBIN=VAL

Can be specified to simplify the histograms printed out in the .chi file, if they are difficult to read if most of the samples are in the same bin. If there are more than MAXRELBIN\% of the samples in the same bin, then that bin will be expanded recursively, and a new histogram will be printed out for that bin. This corresponds to a zoom in each of the bins which contain too much samples. Default value is -1 , i.e. this option is not active by default.

- MONITOR

Monitor the evolution of certain quantities. Eldo will flush out from the . $w d b$ file the average and standard deviation of extracts (.EXTRACT) and measurements (.MEAS) versus the Monte Carlo run index in order to see how these entities evolve. Eldo will also flush out of the.$w d b$ file the expressions used in the AUTOStOp criteria.

- AUTOSTOP=expression

Automatically stops the Monte Carlo process based on the convergence of some or all of the quantities defined in the expression. The expression in the autostor clause is a boolean expression using the mCconv extracts as described in "Monte Carlo Convergence" on page 1218.

- SAVE=mc_file

Saves any relevant information to a specific file. This files can then be used start a new session inheriting the results from the saved session. This save feature is disabled when multiple run commands are specified (.STEP, multiple .TEMP, .AGE, and .MPRUN).

- RESTART=mc_file

Restarts a Monte Carlo simulation run from a previous session on the same design saved with the .MC ... SAVE=mc_file specification. If the file, mc_file, does not exist Eldo generates a warning and performs a normal Monte Carlo run. If a restart file is specified, it means that the number of runs indicated on the command is the additional number of runs.
Topology or stimuli condition changes are allowed, but are not meaningful. The histogram and Monte Carlo statistics reported at the end of an incremental Monte Carlo "session" are computed using data from the previous session. The waveforms displayed versus the run index display the total information, that is, combine the successive runs.

## Assign Nominal Parameter Values

In the second step, each Monte Carlo parameter is assigned a nominal value, a standard deviation (expressed in an absolute value or a relative percentage of the nominal), and LOT/DEV correlation. These are the available probability functions:

## Uniform

Uniform probability, as it sounds, spreads the probability evenly over the sample space. The probability of a sample occurring outside of $\sigma$ of the nominal value is zero. This is the default probability function.


## Gaussian

A Gaussian probability function resembles a bell curve. In Eldo, the curve is truncated at 46 . Note that the probability of a sample landing $\sigma$ of nominal is $68.3 \%$, and within 36 of nominal is $99.99 \%$.


## User-defined

An arbitrary model can be defined through the .DIStrib command. Please refer to ".DISTRIB" on page 614 for more details.

## LOT/DEV Correlation

Monte Carlo parameters can be correlated or not. For example, capacitors in an IC design may have correlation, for example their capacitance values tend to rise or fall together. This is LOT correlation. However, components on a printed circuit board tend not to be correlated, which is DEV correlation. LOT causes devices to vary with each other. DEV causes devices to vary independently of each other.

Parameters can have both LOT and DEV variation. Using both means that affected devices have a degree of independence, even though they are correlated. If a parameter is not a primitive, but depends on parameters with no LOT/DEV specification, then a LOT /DEV specification can be set on that parameter.

A $20 \%$ LOT setting with a 5\% DEV setting for a uniform distribution means that the parameter may not exceed $25 \%$ off of nominal. Furthermore, devices that share that parameter are assigned the $20 \%$ LOT variation together (s1); then, individual $5 \%$ DEV variations are assigned based on s1, instead of the nominal value.

## Note



DEV variation specified with .MODEL statements (or .MCMOD) can refer to dimensions of the current object directly, without any need to encapsulate models into subcircuits. The syntax for accessing an instance parameter is for example:
E(*,<instance_parameter_name>)
The * character is used here to refer to the current instance.

A LOTGROUP can be defined to share the same distribution between dissimilar elements. Once a LOTGROUP is defined, it is used in the same way as LOT or DEV. See the Define Monte Carlo Parameters section below for an example.

```
.LOTGROUP group_name[/distrib_type]=val[%]
```


## Define Monte Carlo Parameters

Monte Carlo parameters are defined through .model, .model with .mCmod, or .param statements.

## .MODEL

Individual model parameters can be given different probability functions. To invoke this, a DEV and/or LOT parameter must immediately follow the model parameter. For example:

```
.model n nmos vto=0.6 dev=0.4 tox=1.5e-7
```

defines a NMOS model with vto set to 0.6 V and tox set to $1.5 \mathrm{e}-7$. The model parameter vto has a uniform distribution with $\sigma=0.4 \mathrm{~V}$, but tox is a constant. The following specification is equivalent:

```
.model n nmos vto=0.6 dev=66.67% tox=1.5e-7
```

In order to use a Gaussian distribution, the DEV parameter is changed to DEV/GAUSS. Using the same example, changing the vto distribution to Gaussian would alter the .MODEL card as follows:

```
.model n nmos vto=0.6 dev/gauss=0.4 tox=1.5e-7
```

If a . Lotgroup is defined, then that can be used, as well. The Gaussian distribution example can be expressed as:

```
.LOTGROUP group_a/gauss=0.4
```

```
.model n nmos vto=0.6 lotgroup=group_a
.model n2 nmos vto=2.5 lotgroup=group_a
```

A different parameter of a different model using LOTGROUP group_a would have the same distribution. For example, the same number, between +0.4 and -0.4 , will be used for both vto parameters.

Eldo takes into account changes in binning parameters (for example LMIN, LMAX) due to MC variation. Eldo will first make the variations on the . MODEL, and then select at each MC run the appropriate model. For example:

```
.param p1 = 1 dev = 5%
.MODEL N.1 NMOS LMIN = '1u*p1' LMAX = '2u*p1'
.MODEL N.2 NMOS LMIN = '2u*p1' LMAX = '3u*p1'
M1 D G S B N W=1u l = 1u
```

Here Eldo will extract a new random value for p 1 : this value will be used to update parameters of both N. 1 and N.2. When all parameters of the .model have been updated, Eldo will select the appropriate model to be used for device M1.

If both the size of a device and the binning parameters of its model are altered by MC variation, Eldo will issue an error that it cannot handle this situation.

Use option MC_IGNORE_BINNING to disable this automatic selection of the binning parameters at run time; the model selected at the nominal run will then be used for the whole MC process.

## .MCMOD

Modifying .model lines for Monte Carlo analysis can be inconvenient. Eldo offers the .mсmod command to assign probability functions for .MODEL parameters without changing any part of the .model statement.

```
.MCMOD model [(list_of_instances)] param1 LOT|DEV=val1
+ [{param2 LOT|DEV=val2 param3 LOT|DEV=val3 ...}]
```

The .MODEL name must be specified, followed by one or more pairs of parameters and LOT and/or DEV values. Optionally, a list of instances will apply the Monte Carlo probabilities to only instances in that list.

Using the example above, the Monte Carlo parameter may be written as:

```
.model n nmos vto=0.6 tox=1.5e-7
.mcmod n vto dev=0.4
```


## .PARAM

The syntax for Monte Carlo . Param parameters is different than for .model parameters. There are two ways to use .PARAM. The simpler of the two ways is outlined; please refer to ".PARAM" on page 778 for additional details.

```
.PARAM param1=UNIF|AUNIF|GAUSS|AGAUSS|LIMIT({option_list})
```

- UNIF (nom, rel)

Defines a uniform distribution. The parameter param1 varies uniformly between nom-nomXrel and nom + nomXrel.

- AUNIF (nom, abs)

Defines a uniform distribution. The parameter param1 varies uniformly between nom -abs and nom + abs.

- GAUSS (nom, rel, sigcoef)

Defines a Gaussian distribution. The curve is centered around nom, and the standard deviation is given by $\sigma=($ nom $\times$ rel $) \div$ sigcoef.

- AGAUSS (nom, abs, sigcoef)

Defines a Gaussian distribution. The curve is centered around nom, and the standard deviation is given by $\sigma=$ abs $\div$ sigcoef.

- Limit (nom, abs)

Defines a limit distribution. Each sample can take the value of nom + abs or nom - abs only, with equal probability.

When defining a parameter using Monte Carlo distribution, variation on the parameter differs depending on where the parameter is specified. цот variation is used when a defined parameter affects model parameters, this means the same random value will be used each time it affects a separate model parameter. DEV variation is used when a parameter affects instance parameters, an independent random value is calculated each time the parameter is specified.

## Correlation

A correlation coefficient can be set up between parameters. Please refer to ".CORREL" on page 575 for details.

## Monte Carlo Output

At the end of a Monte Carlo simulation, Eldo prints in the .chi file a histogram for each .EXTRACT command, see ".EXTRACT" on page 637. The number of bins for the histogram can be specified in the .mc command using the nbbins parameter. The default is 10 .

Note
The histogram is also output in the binary output file and can be displayed with EZwave.

The example below shows the .chi file entry for a Monte Carlo analysis (of least nine runs) with the following . EXTRACT command:

```
.EXTRACT tran label=tpd tpdud(v(in), v(out))
Distribution of TPD
```

|  | Range [ 9 <br> Nominal v <br> Average v <br> Standard <br> Standard | $9.8405 \mathrm{E}-10$ <br> value: 1.3 <br> value: 1.2 <br> Deviation: <br> Deviation | $\begin{aligned} & 1.7374 \mathrm{E}-09] \\ & 124 \mathrm{E}-09 \\ & 709 \mathrm{E}-09 \\ & 1.9007 \mathrm{E}-10 \end{aligned}$ <br> based on nominal | run: $1.3124 \mathrm{E}+00$ |
| :---: | :---: | :---: | :---: | :---: |
| [ 984.00000P | 1.06060 N | ] $\mathrm{NB}=2$ | FREQ $=1.00 \mathrm{e}+01 \%$ | ***** |
| [ 1.06060N | 1.13720 N | ] $\mathrm{NB}=3$ | FREQ $=1.50 \mathrm{e}+01 \%$ | ******* |
| [ 1.13720N | 1.21380 N | ] $\mathrm{NB}=5$ | FREQ $=2.50 \mathrm{e}+01 \%$ | *********** |
| [ 1.21380N | 1.29040 N | ] $\mathrm{NB}=1$ | FREQ $=5.00 \mathrm{e}+00 \%$ | ** |
| [ 1.29040N | 1.36700 N | ] $\mathrm{NB}=4$ | FREQ $=2.00 \mathrm{e}+01 \%$ | ********** |
| [ 1.36700N | 1.44360 N | ] $\mathrm{NB}=1$ | FREQ $=5.00 \mathrm{e}+00 \%$ | ** |
| [ 1.44360N | 1.52020 N | ] $\mathrm{NB}=2$ | FREQ $=1.00 \mathrm{e}+01 \%$ | ***** |
| [ 1.52020N | 1.59680 N | ] $\mathrm{NB}=1$ | FREQ $=5.00 \mathrm{e}+00 \%$ | ** |
| [ 1.59680N | 1.67340 N | ] $\mathrm{NB}=0$ | FREQ $=0.00 \mathrm{e}+00 \%$ |  |
| [ 1.67340N | 1.75000 N | ] $\mathrm{NB}=1$ | FREQ $=5.00 \mathrm{e}+00 \%$ | ** |

Two standard deviation results are provided:

- "Standard Deviation" is the RMS value of the deviation of output with respect to the average value;
- "Standard Deviation based on nominal run" is the RMS value of the deviation of output with respect to the nominal run.

A summary of the extracted Monte Carlo distribution results can be written to the .aex file and the file specified in the .EXTRACT command using the option dump_mcinfo, see "DUMP_MCINFO" on page 999 for more information.

In addition to the standard .EXTRACT arguments, see ".EXTRACT" on page 637, the following arguments specific to Monte Carlo analysis can be specified:

## - LBOUND

Lower bound of the value range

- ubound

Upper bound of the value range
A Monte Carlo analysis can use this information to determine whether the extracted value remains in the range [Lbound, ubound] during the Monte Carlo analysis, and display a report at the end of the ASCII output (.chi) file. For example:

```
.extract label=toto yval(v(s),25n) lbound=0.43 ubound=0.44
```

This may result in something like the below:

```
Distribution of TOTO
    Range [ 420.84593M 461.95279M]
    Nominal value: 440.36822M
    Average value: 443.83611M
    Standard Deviation: 12.80183M
    Passed : 4 ( 20.00000 %)
```

```
*** MC runs which passed all extract: 4 ( 20.0000 %)
MC run 5 OK
MC run 9 OK
MC run 12 OK
MC run 17 OK
```

Additional parameters can be specified on the .EXTRACT command to extract the minimum, maximum, mean and the standard deviation values, together with higher order moments:

- MCMIN(label)

Returns the minimum value of the selected extract

- MCMAX(label)

Returns the maximum value of the selected extract

- MCNBECH(label)

Returns the number of measured values for the selected extract

- MCAVG(label)

Returns the average value of the selected extract

- MCSTD (label)

Returns the standard deviation of the selected extract

- mCVAR(label)

Returns the variance of the selected extract

- MCSKEW (label)

Returns the skewness of the selected extract, computed as the moment of order 3

- mCKURT (label)

Returns the kurtosis of the selected extract, computed as the moment of order 4

- MCMOM(label, center_value, order)

Returns for the selected extract, the moment of order centered on the value center_value

## Note

Keyword mс is required on the .ехтRACT statements which make use of these Monte Carlo extract functions.

## Examples:

```
.EXTRACT AC LABEL=myextract MAX(VDB(s))
. EXTRACT MC MCKURT (myextract)
.EXTRACT MC
+ MCMOM (myextract,MCAVG (myextract), 4.0/MCSTD (myextract)**2)
```

The third line is equivalent to the mckurt function.

## Monte Carlo Convergence

Specify the mcconv function to control the run-length in the context of sequential Monte Carlo algorithms for estimating $E(Y)$, in contrast to fixed run-length approaches, we generate samples until some error criterion is satisfied.

Two algorithms (SETTLING and CONFIDENCE) are provided to control the convergence. We can monitor the evolution of the various moments AVG for the CONFIDENCE method and AVG, STD, KURT and SKEW for the SETTLING method to precisely quantify the notion of convergence. The Monte Carlo process can be stopped early if these quantities do not vary more than a user-specified limit.

Recall the simulation framework we use when we want to estimate $\theta=E[Y]$ :

- we first simulate $Y_{1}, Y_{2}, \ldots, Y_{n}$ and set $\hat{\theta}_{n}=\frac{Y_{1}+Y_{2}+\ldots+Y_{n}}{n}$
- the strong Law of Large Numbers says: $\hat{\theta}_{n} \rightarrow \theta$ as $n \rightarrow \infty$

But at this point we do not know how large $n$ should be so that we can have confidence in $\hat{\theta}_{n}$ as an estimator of $\theta$. Put another way, for a fixed value of $n$, what can be said about the quality of $\hat{\theta}_{n}$ ?

One way to answer this question is to use a confidence interval. Suppose we want to estimate $\theta$ and we have a random sequence $Y_{1}, Y_{2}, \ldots, Y_{n}$ whose distribution depends on $\theta$. Then we seek $L(Y)$ and $U(Y)$ such that $\operatorname{Prob}(L(Y) \leq \theta \leq U(Y))=1-\alpha$
where $0 \leq \alpha \leq 1$ is a pre-specified number. We then say that $[L(Y), U(Y)]$ is a $100(1-\alpha) \%$ confidence interval for $\theta$.

There are two types of error that we can consider:

- the absolute error, which is given by $E_{a}=\left|\hat{\theta}_{n}-\theta\right|$ and
- the relative error, which is given by $E_{r}=\left|\frac{\hat{\theta}_{n}-\theta}{\theta}\right|$

Now we know that $\hat{\theta}_{n} \rightarrow \theta$ as $n \rightarrow \infty$ so that the errors both tend to 0 . If $\theta=0$ then the relative error $E_{r}$ is not defined. We specify the following error criterion:

Error Criterion: Given $0 \leq \alpha \leq 1$ and $\varepsilon>0$, we want $\operatorname{Prob}(E \leq \varepsilon)=1-\alpha . E$ is the error type we have specified (relative or absolute).

Suppose that we wish to satisfy the condition $\operatorname{Prob}\left(E_{a} \leq \varepsilon\right)=1-\alpha$, then we continue to generate samples until

$$
\frac{\hat{\sigma}_{n} \cdot z_{1-\alpha / 2}}{\sqrt{n}} \leq \varepsilon
$$

where $z_{1-\alpha / 2}$ is the $(1-\alpha / 2)$ percentile point of the $N(0,1)$ distribution and $\hat{\sigma}_{n}$ is again the estimate of $\sigma$ based upon the first samples. It is important that $n$ be sufficiently large $n \geq p$, so that $\hat{\theta}_{n}$ and $\hat{\sigma}_{n}$ are sufficiently good estimates of $\theta$ and $\sigma$ respectively. As a result, we typically insist that $p=20$ before we stop.

If we want to control the relative error and have $\operatorname{Prob}\left(E_{r} \leq \varepsilon\right)=1-\alpha$, then we would simulate samples until

$$
\frac{\hat{\sigma}_{n} \cdot z_{1-\alpha / 2}}{\hat{\theta}_{n} \sqrt{n}} \leq \varepsilon
$$

The settiding method simply controls the absolute and relative errors as if the Monte carlo procedure was a deterministic process. In other words, we use the simple test $E \leq \varepsilon$.

The convergence is associated to a 'pseudo-extract' in the Eldo's language for extraction. The mCConv extract returns 0 or 1 depending on a specific test.

- MCCONV (meas_name, AVG|STD|KURT|SKEW, SETTLING|CONFIDENCE [, PARAMETER_LIST])

Returns 1 or 0 to indicate convergence of the Monte Carlo process for the specified quantity.

## SETTLING

The Monte Carlo process is stopped if adding new samples no longer changes output by more than a certain threshold. When the settuing algorithm is specified, the PARAMETER_LIST is: WINDOW[,ABSTOL[,RELTOL].

## CONFIDENCE

The Monte Carlo is stopped when the confidence interval is small. This algorithm is defined for AVG only; not for STD, SKEW or CURT. When the confidence algorithm is specified, the PARAMETER_LIST is: WINDOW[, CONFIDENCE_LEVEL[,ABSTOL[,RELTOL]].
Examples:

```
.EXTRACT AC LABEL=gain_db yval(vdb(out), 1MEG)
.EXTRACT MC L_ABEL=stddev_gain__db_conv
+ MCCONV(gain_db, STD,SETTLING, 0.01, 0.05, 20)
```

The second extract returns a boolean value ( 1 or 0 ). It returns 1 when the standard deviation of quantity gain_db has converged to within $+/-(0.01+5 \% \times \mathrm{M})$ where M is the average value of the STD taken from the last 20 MC samples.

```
.EXTRACT AC LABEL=gain_db yval(vdb(out), 1MEG)
.EXTRACT AC LABEL=phase_db yval(vp(out), 1MEG)
.EXTRACT DC LABEL=cC i(vdd)
.EXTRACT MC LABEL=mc_std_conv MCCONV(ALL, STD, 20, 0.01,0.05)
```

In this example, the first three . Еxtract statements are considered, and all three of them must have converged before the mCconv () function returns 1 .

We recommend to not waste time in tolerance tuning. Use the default values as much as possible, for instance

```
.EXTRACT MC LABEL=mc_avg_conv MCCONV (ALL, AVG, CONFIDENCE)
```

should give a first estimate of the uncertainty, and use the SAVE/RESTART feature to obtain more accurate estimates.

The threshold and sample window size are optional. Their default values can be (re)defined on the .mC command.

## Extracting the Index and Total Number of Runs

Specify the following arguments to extract the index of the current run and the total number of runs.

- ICARLO

Extracts the index of the current Monte Carlo run (first index is 0 )

- nBCARLO

Extracts the total number of Monte Carlo runs
Example:

```
.option aex dump_mcinfo
.param rval=1k dev=10%
v1 0 1 dc 1
r1 1 0 rval
.extract dc label=test {i(v1)/(1+ICARLO)}
.dc
.mc 10 all
```


## Statistical Configuration

The keyword, statistical $=0 \mid 1$, can be specified on X instances, device declarations, or on . Subckт definitions, to specify whether any statistical variation due to .mc, . WCASE, or .DCMISMATCH can be applied to the specified entities.

If statistical is 0 , the selected devices will keep their nominal values. If statistical is 1 , the selected devices have statistical variation applied. The global default value can be specified via option statistical $=0 \mid 1$. Default is 1 .

See the Statistical Configuration Usage Example.

## Examples

The effects of Monte Carlo analysis can be seen easily in a simple passive low-pass filter.

```
.model c cap dev=20%
.model r res lot=20% dev=5%
.mc 20 all
v1 vin 0 ac=1 dc=1
r1 vin a r 1k
c1 a 0 c 10p
.ac dec 10 100 1e8
.probe v
.end
```

The capacitor model has DEV of $20 \%$, so all capacitors using this model are uncorrelated and vary up to $20 \%$ from the nominal value specified in the element instantiation. Capacitor C1 varies uniformly between 8 pF and 12 pF . The resistor model produces resistors that are correlated with a $20 \%$ deviation. After Eldo applies the $20 \%$ LOT variation, each resistor has a $5 \%$ non-correlated variation.

The ALL argument to .mc tells Eldo to save the result from every Monte Carlo iteration. Otherwise, only the average, maximum, and minimum values are saved.

Running this simulation and viewing the voltage at node a produces the following graph.

Figure 19-1. Monte Carlo Analysis Example


Device sizes can be subject to a probabilistic distribution, simulating process variation, through the use of . PARAM statements. In this next example, the NMOS transistor's width follows a Gaussian curve, centered around $20 \mathrm{e}-6$ with $\sigma=0.2 \times 20 \mathrm{e}-6=4 \mathrm{e}-6$ as defined by parameter nwidth. This parameter will also be subject to dev variation. A .Extract measures the propagation time through the inverter. The .chi file contains statistical information about the outcome of the .EXTRACT.

```
.model n nmos level=1
+ vto=1.2
+ kp=2.5e-5
+ gamma=1.5
.model p pmos level=1
+ vto=-1.5
+ kp=1.2e-5
+ gamma=1.2
.param nwidth=gauss(20u,0.2,1)
m1 out in vss vss n w=nwidth l=15u
m2 out in vdd vdd p w=30u l=15u
```

```
cout out 0 0.1p
vdd vdd 0 5
vss vss 0 0
vin in 0 pwl (0 0 50n 0 51n 5)
.mc 20 all
.tran 1n 100n
.probe tran v(out)
.extract tran label=tpd tpdud(v(in), v(out))
.end
```

The . PARAM usage may be applied to model parameters, as well. The vto of the NMOS transistor can be replaced with a Gaussian parameter. In this case, the standard deviation $\sigma$ is 0.24 . This technique may be more useful if the parameter needs to be a mathematical function of several variables.

```
.model n nmos level=1
+ vto=nvto
+ kp=2.5e-5
+ gamma=1.5
.model p pmos level=1
+ vto=-1.5
+ kp=1.2e-5
+ gamma=1.2
.param nvto=gauss(1.2,0.2,1)
m1 out in vss vss n w=20u l=15u
m2 out in vdd vdd p w=30u l=15u
cout out 0 0.1p
vdd vdd 0 5
vss vss 0 0
vin in 0 pwl (0 0 50n 0 51n 5)
.mc 20 all
.tran 1n 100n
.probe tran v(out)
.extract tran label=tpd tpdud(v(in), v(out))
.end
```

Each instance of a transistor using the NMOS model will have the same value of vto because nvto affects a model parameter and therefore цот variation is used.

The following is an example of the statistical configuration usage:

```
.model r r tc1 = 2 lot = 5% dev = 10%
```

```
.subckt r a b
r1 a b r 1k
.ends
i1 1 0 pwl ( 0 1 10n 10)
x1 1 2 r statistical=0
x2 2 3 r
x2 3 0 r
.tran 1n 10n
.extract dc v(1)
.temp 10
.mc 10
.end
```

In the above, X1.R1 will remain at its nominal value during Monte Carlo analysis. This is because statistical is set to 0 for X 1 .

```
.model r r tc1 = 2 lot = 5% dev = 10%
.subckt r a b
rl a b r 1k
.ends
i1 1 0 pwl ( 0 1 10n 10)
x1 1 2 r
x2 2 3 r statistical=1
x2 3 0 r
.tran 1n 10nx2
.extract dc v(1)
.temp 10
.mc 10
.option statistical=0 ! consider devices non-statistical by default
.end
```

In the above, only X2.R1 will vary during Monte Carlo analysis. This is because the global statistical option is set to 0 meaning devices are considered non-statistical by default, but this is overridden by the statistical keyword set to 1 for X 2 .

The following is an example showing how sigbin can be specified to truncate the histogram to a certain number of sigmas.

```
* analyze main distribution when there are atypical values
v1 1 0 val
.param val=1 dev/trimodal=0.00002
.distrib trimodal
+ (-1 0) (-0.999 0.1) (-0.998 0)
+(-0.1 0) ( 0 1 ) ( 0.1 0)
+( 0.998 0) ( 0.999 0.1) ( 1 0)
.extract dc label=v1 v(1)
.extract dc label=v1_norm '(v(1)-1.0)*1'
.dc
*
.mc 2000 print_extract=all sigbin=4
.end
```

Specifying sigbin a value of 4 means atypical values are ignored for computing the min/max for the histogram. Eldo will gather all the samples above "mean + SIGBIN $\times$ sigma" in the Above bin, and all the samples below "mean-SIGBIN $\times$ sigma" in the Below bin.

# Chapter 20 <br> Statistical Experimental Design and Analysis 

## Introduction

## Overview

This chapter is concerned with the standard techniques of factor screening, location and dispersion analysis and response surface methodologies in circuit design. In this context, a general situation is considered where an observable output (extracted measure in Eldo) depends on a set of parameters and the effects (main effects and interactions) of parameters (factors) on the output are explored using the techniques of Design of Experiments.

This release contains only the basic tools to perform a factor screening experiment. Because the main issue in studying statistical design problems lies in a large number of circuit parameters involved, the primary purpose of a variable screening experiment is to select or screen out the few important main effects from the many less important ones. The Eldo command .DEx can be used to perform a factor screening. Once a small number of important factors is identified, subsequent statistical design problems can be solved more efficiently and require fewer runs.

In this context, a factor is a circuit parameter that is studied in the experiment. In order to study the effect of a factor on one or several user-defined responses, two or more values of the factor are used. These values are referred to as levels or settings. A combination of factor levels is called a run and will be associated to a specific simulation run in Eldo.

In an experiment, we deliberately change one or more variables (or factors) in order to observe the effect the changes have on one or more response variables. The DEX techniques are efficient procedures so that the data obtained can be analyzed to yield valid and objective conclusions. This efficiency is founded on some key properties of orthogonal arrays, which offer a systematic way of testing. The benefits include: a uniform distributed coverage of the test domain, all pair-wise combinations of test set created, and arrive at complex combinations of all the variables.

## Practicalities

We wish to emphasize in advance that the procedures implemented in this command should be qualified by the designer. Although many of these methods are part of the current state of the art, the issue of deciding when a computed answer is correct is difficult.

For instance, it is important to note that the quantitative techniques used for factor screening are incomplete in nature because they are numeric summaries. By reducing the data to a few numbers, we filter the data, omit and screen out other sometimes crucial information.

The following lines give some practical considerations:

- The factor screening algorithms use two-level designs, because they require fewer runs and are more economical to conduct. In two-level experiments, only the linear effects can be studied, three-level factors should be considered to detect a curvature effect. For example, the factor "temperature" may affect the responses in a non-monotone way. The use of only two temperature levels ("High" and "Low") represents a strong assumption about the relation between the responses and the temperature.
- The screening designs employed in the DEX analysis are based on Hadamard matrices, which are an important class of orthogonal arrays. In such designs the main effects are, in general, heavily confounded (or aliased) with two-factor interactions. For this reason, it may be difficult to treat the large number of aliased effects and to interpret their significance. It may happen that the main effect analysis does not very well explain the variation in the user-defined response.


## Main Effects Analysis and .WCASE Command

When the main effects are investigated, the following main effect model around the nominal point $x^{0}$ is assumed:

$$
y(x)=y_{0}+\sum_{i=1}^{n} \alpha_{i}\left(x_{i}-x^{0}\right)
$$

As noted above, this model can be applied to the following cases:

- interactions can be tentatively assumed to be zero,
- in screening a large set of factors, some factors with large main effects on the output $y$ exist.

A traditional engineering way to estimate the coefficients $a_{i}$ has been based on a single or double-sided sensitivity analysis, which can be called the "one-factor-at-a-time" method. This approach is used in the sensitivity computations of the . WCASE command. In this case, each of the variables $x_{i}$ is perturbed by $\pm \Delta x_{i}$ (where $\Delta x_{i}$ is the difference between the "High" and "Low" level values of the $i$ th parameter) about the nominal point $x^{0}$, keeping all the others at their nominal values.

By comparison with the factorial design method implemented in the DEX procedures, it has the following disadvantages:

- it cannot estimate some interactions,
- the conclusions from its analysis are not general,
- it can miss optimal settings of factors.

Intuitively, this can be seen from the fact that the one-factor-at-a-time plan does not conduct a systematic or comprehensive search over the experimental region.

The . WCASE command also provides the so-called worst case values of the response $y(x)$ where x is replaced by the following 'worst case points':

$$
\left(x_{1}+\Delta x_{1}, x_{2}+\Delta x_{2}, \ldots, x_{n}+\Delta x_{n}\right),\left(x_{1}-\Delta x_{1}, x_{2}-\Delta x_{2}, \ldots, x_{n}-\Delta x_{n}\right)
$$

where the coordinates are all set to their extreme values: 'High' $x_{i}+\Delta x_{i}$, or 'Low' $x_{i}-\Delta x_{i}$.
These points, which are not necessarily the true worst case points, are systematically tested when the selected screening design uses about 2 n runs (this is the default argument of the DESIGN argument of the .DEX command).

## Analysis Statement

In order to use the .DEX command, the designer must provide the following information:

- the nominal circuit, which is identical to the circuit provided for simulation in the netlist format. The user must have a working netlist.
- The factors, the designer must specify those parameters that may be considered by the command when conducting the experiment. The designer's selection of factors is accomplished by adding minor modifications to the working netlist, using the . Paramdex command. Please refer to the section ".PARAMDEX" on page 1239.
- The response may be any quantity represented by a real value, a combination of quantities. This response function is specified by the .Extract and .meas commands.

For example, the . Paramdex command is used to specify the length $L$ and the width $w$ of a MOS transistor:

```
.PARAMDEX
+ L CTRL/ REL=20%
+ W CTRL/ REL=20%
```

this command defines the levels (or settings) of L and W as follows:

$$
\left\{\begin{array}{c}
L \\
W
\end{array}\right\}_{\text {low }}=\left\{\begin{array}{c}
L \\
W
\end{array}\right\}_{n o m}-0.80 \cdot\left\{\begin{array}{c}
L \\
W
\end{array}\right\}_{n o m}
$$

and:

$$
\left\{\begin{array}{c}
L \\
W
\end{array}\right\}_{h i g h}=\left\{\begin{array}{c}
L \\
W
\end{array}\right\}_{n o m}+1.20 \cdot\left\{\begin{array}{c}
L \\
W
\end{array}\right\}_{n o m}
$$

## Running the Experiment

The .DEx command is part of the Eldo commands. Eldo can be invoked from the command line as follows:
eldo <circuit_name> <other_arguments>

## Commands

The following are commands that can be used for experimental design:

- .DEX
- .PARAMDEX

In the descriptions inside this chapter we use the tokens IVALUE and rValue to denote integer and real (or floating) numbers.

## .DEX

The Eldo command .DEX can be used to perform factor screening before attempting to solve subsequent statistical problems. The primary purpose of a variable screening experiment is to select or screen out the few important main effects from the many less important ones. Note that the .Dex command is compatible with the Multiple Run features (see the command description for ".MPRUN" on page 729).

The maximum number of factors $N_{\max }$ is 40000 . This number is the result of the algorithm we used for the construction of Hadamard matrices. All Hadamard matrices of orders N up through 28 , and at least one of every order N up through 200 are not computed, but stored explicitly in the static memory. Higher orders are obtained implicitly by computing Kronecker products $H_{1} \otimes H_{2}$. If $H_{1}$ and $H_{2}$ are Hadamard matrices of order $N_{1}$ and $N_{2}$, then the previous direct product is a Hadamard matrix of order $N_{1} N_{2}$.

It is not recommended to run very large experiments. Most of our test-cases involved a moderate number of factors, say up to 50 . Note that the range 7 to 150 should be considered as a safe area of operatability for the Lenth's method.

Figure 20-1 depicts the geometrical differences between a full factorial design and an orthogonal arrays based on Hadamard matrices.

Figure 20-1. Cuboidal representation of two 3-factors designs


The black bullets indicate that the corners are effectively chosen. The first design is obtained by setting the argument DESIGN=FULL_FACT and the second by DESIGN=ORTHA_2_n. One can clearly observe that the last design is a balanced subset of the full factorial design.

## Command Syntax

The main effect analysis acting on all the circuit parameters defined with the .PARAMDEX statement is defined as follows:

```
.DEX
+ EXPERIMENT = SCREENING | SCREENING_CTRI | SCREENING_NOISE
```

```
RESPONSE = LIST_OF_MEASURES
[DESIGN = ORTHA_2_N | ORTHA_2_2N | FULL_FACT]
[FACTOR = LIST_OF_FACTORS]
+ [FIND_FACTOR]
```


## Parameters

- EXPERIMENT=SCREENING|SCREENING_CTRL|SCREENING_NOISE

A screening experiment will be conducted on the performance response defined with the argument response. The factors will be taken from the list of circuit parameters appearing on a . PARAMDEX statement. The results of this experiment are available in the .dex file. This output file contains an ordered data table for each simulated response, a DEX mean table which provides the ranked list of factors (not including the interactions), the ranking is from the most important factor to least important factor, and a formal test of significance based on the Lenth's method. The additional analyses screening_ctri and screening_noise can be used to filter out the noise and designable parameters respectively for a screening experiment. This option is particularly useful for identifying the critical noise factors and critical designable factors separately, please consult the section "Two-stage Strategy for the Identification of Critical Factors" for details of this approach.

- RESPONSE=LIST_OF_MEASURES

List of comma-separated measures to be considered in the experiment.

- FACTOR=LIST_OF_FACTORS

List of comma-separated circuit parameters specified with the .PARAMDEX command to screen out. By default, all the circuit parameters defined with the .PARAMDEX command are used in the factor screening.

- DESIGN=ORTHA_2_N|ORTHA_2_2N|FULL_FACT

The category of the design matrix used to run the experiment. The arguments ORTHA_2_N and ORTHA_2_2N specify that an orthogonal array at two levels with economical run size based on Hadamard matrices has to be chosen. If $N$ is the number of factors, the design ORTHA_2_N will use about $N$ runs, and ORTHA_2_2N and $2 N$ runs. A full factorial design $2^{N}$ can also be used when the number of factors is small (say $N<7$ ), because it requires $2^{N}$ runs.

Default is: ORTHA_2_2N.

- FIND_FACTOR

This option will return the list of process parameters (noise factors) which are candidates for the .DEx command. When this argument is activated the DEX analysis is not performed.

## Results and Output of the SCREENING Experiment

The results of this analysis are presented below. The example used is cmos_ring.cir (available in the directory: \$MGC_AMS_HOME/examples/optimizer/). Two response functions are defined which are the oscillation frequency $30 \mathrm{MHz}<$ OSCFREQ $<50 \mathrm{MHz}$, and the AC switching power dissipation: ACPOWER < 5 MW.

This analysis is performed with respect to 34 noise factors. Note that the .dex file gives the name and the properties of each factor. A dummy name is associated to each factor in order to get more compact tables. The control factors are designated by $\mathrm{c} 1, \mathrm{C} 2, \mathrm{c} 3, \ldots$ and the noise factors by N1, N2, N3, and so on.

```
Factors and Levels
    ==> Level values and coded factors
    ==> Output in the following order:
        Distrib ... Statistical distribution of factor (Uniform or Gaussian)
        Coding ... Levels are coded with the Std. Deviation
        Mult ... Fraction of the Std. Deviation or the Range
        Dev/Range ... Std. Deviation or Range
        Mean ... Mean value of the statistical distribution
        Low/High ... Low and High settings (coded with -1 and +1)
Noise Factor(s)
    N1 - M(SBSIMP,X3U1)
    Distrib Coding
    Gauss StdDev 1.0e+00 2.8900e-03
    1 M(SBSIMP X3MS)
    N2 - M(SBSIMP,X3MS) Gauss StdDev 1.0e+00 1.4400e+00 ...
    N2 - M(SBSIMP,X3MS) Gauss StdDev 1.0e+00 1.4400e+00 ...
    N3 - M(SBSIMP,X2MS) Gauss StdDev 1.0e+00 1.4700e+00 ...
    N4 - M(SBSIMP,MUS) Gauss StdDev 1.0e+00 2.2100e+01 ...
    N5 - M(SBSIMP,X2U1) Gauss StdDev 1.0e+00 2.1400e-03 ...
    N6 - M(SBSIMP,X2U0) Gauss StdDev 1.0e+00 7.7600e-04 ...
    N7 - M(SBSIMP,X3E) Gauss StdDev 1.0e+00 7.6500e-04 ...
    N8 - M(SBSIMP,X2E) 
...
    N29 - M(SBSIMN,MUZ) Gauss StdDev 1.0e+00 4.6100e+01 ...
    N30 - M(SBSIMN,ETA) Gauss StdDev 1.0e+00 5.3200e-03 ...
    N31 - M(SBSIMN,K2) Gauss StdDev 1.0e+00 3.7800e-02 ...
    N32 - M(SBSIMN,K1) Gauss StdDev 1.0e+00 1.1900e-01 ...
    N33 - M(SBSIMN,PHI) Gauss StdDev 1.0e+00 1.0800e-02 ...
    N34 - M(SBSIMN,VFB) Gauss StdDev 1.0e+00 8.0600e-02 ...
```


## Ordered Data Table

An ordered data table for each simulated response, this data table answers the following basic question: what is the best setting (based on the data) for each of the N factors? An ordered data table is formed by:

- vertical axis: the ordered (smallest to largest) raw response value for each runs in the experiment.
- horizontal axis: the corresponding factor index with (at each run) a designation of the corresponding settings $(-1$ or +1$)$ for each of the N factors.

This analysis can be found in the .dex file as follows:

```
Ordered Data Table
```

```
Response Y : OSCFREQ
Mean Value : 4.8667e+07
Value at nominal point : 4.8667e+07
==> Vertical axis: the ordered raw response
        value for each of the 72 runs in the experiment.
        Horizontal Axis: the corresponding dummy variable index (1 to 34)
        with settings (-1 or +1) for each of the 34 factors.
\begin{tabular}{rrllllllllllr} 
Run & N1 & N2 & N3 & N4 & \(\ldots\) & N29 & N30 & N31 & N32 & N33 & N34 & Response Y \\
4 & +1 & -1 & -1 & -1 & & +1 & -1 & +1 & +1 & +1 & -1 & \(4.1226377 \mathrm{e}+07\) \\
56 & -1 & +1 & +1 & -1 & & +1 & -1 & +1 & +1 & +1 & +1 & \(4.1369450 \mathrm{e}+07\) \\
31 & -1 & -1 & +1 & -1 & & -1 & -1 & -1 & +1 & +1 & +1 & \(4.2162628 \mathrm{e}+07\) \\
72 & +1 & +1 & -1 & -1 & & -1 & -1 & -1 & -1 & -1 & +1 & \(4.2545442 \mathrm{e}+07\) \\
15 & -1 & -1 & +1 & -1 & & -1 & +1 & +1 & -1 & +1 & +1 & \(4.2712903 \mathrm{e}+07\) \\
61 & +1 & +1 & -1 & +1 & & +1 & +1 & -1 & +1 & -1 & +1 & \(4.3002165 \mathrm{e}+07\) \\
11 & +1 & -1 & +1 & -1 & & +1 & +1 & -1 & +1 & +1 & -1 & \(4.3099024 \mathrm{e}+07\) \\
14 & -1 & +1 & -1 & +1 & & +1 & +1 & -1 & +1 & +1 & -1 & \(4.3174847 \mathrm{e}+07\) \\
19 & -1 & -1 & +1 & -1 & \(\ldots\) & +1 & -1 & -1 & -1 & -1 & +1 & \(4.3490089 \mathrm{e}+07\)
\end{tabular}
```


## DEX Mean Table

A DEX mean table which provides the ranked list of factors (not including the interactions), the ranking is from the most important factor to least important factor. This table is appropriate for analyzing data from an experiment, with respect to important factors, where the factors are at two levels. The table gives the mean value and the amplitude of the main effect coefficient (a line proportional to this magnitude is also printed). Note that the magnitude represents the absolute value of the coefficient $a_{i}$.

This qualitative analysis can be found in the .dex file as follows (the central part has been removed):

```
DEX Mean Table
    Response Y : OSCFREQ
    ==> Horizontal axis: the mean response for a given setting (- or +)
        of a factor, for each of the 34 factors.
        Vertical axis: the 34 factors and the two settings (- and +)
        within each factor.
        Value at nominal point : 4.8667e+07
        Mean Value : 4.8667e+07
    Factor Name Sign of Magnitude
```

|  |  | effect | (percent | / exact / | mulative) |
| :---: | :---: | :---: | :---: | :---: | :---: |
| N4 | M (SBSIMP, MUS) | [+] | 13.0\% | $3.6552 \mathrm{e}+06$ | 13.0\% |
| N27 | M (SBSIMN, U1) | [-] | 12.8\% | $3.6022 \mathrm{e}+06$ | 25.8\% |
| N21 | M (SBSIMN, MUS) | [+] | 11.6\% | $3.2592 \mathrm{e}+06$ | 37.3\% |
| N32 | M (SBSIMN, K1) | [-] | 9.9\% | $2.7839 \mathrm{e}+06$ | 47.2\% |
| N15 | M (SBSIMP, K1) | [-] | 7.8\% | $2.1921 e+06$ | 55.0\% |
| N10 | M (SBSIMP, U1) | [-] | 7.5\% | $2.1091 e+06$ | 62.5\% |
| N17 | M (SBSIMP, VFB) | [-] | 6.0\% | $1.6999 \mathrm{e}+06$ | 68.5\% |
| N34 | M (SBSIMN, VFB) | [-] | 5.8\% | $1.6240 \mathrm{e}+06$ | 74.3\% |
| N18 | M (SBSIMN, X3U1) | [+] | 3.1\% | $8.7887 e+05$ | 77.4\% |
| N11 | M (SBSIMP, U0) | [-] | $2.8 \%$ | $7.8008 \mathrm{e}+05$ | 80.2\% |
| N23 | M (SBSIMN, X2U0) | [-] | 0.0\% | $1.5643 \mathrm{e}+03$ | 100.0\% |
| N9 | M (SBSIMP, X2MZ) | [-] | 0.0\% | $7.2275 \mathrm{e}+02$ | 100.0\% |

The last column gives the following information: it says that almost $70 \%$ of the response's variability is explained with the variations of the eight factors M (SBSIM*, MUS), $\mathrm{M}\left(\mathrm{SBSIM}^{\star}, \mathrm{U1}\right), \mathrm{M}\left(\mathrm{SBSIM}^{*}, \mathrm{K1}\right)$ and $\mathrm{M}\left(\mathrm{SBSIM}^{*}, \mathrm{VFB}\right)$ where the ' $\star$ ' character means ' P ' positive or ' N ' for negative.

## Formal Test of Significance

A formal test of significance is based on the Lenth's method. A detailed description of this algorithm can be found in [1]. This method is usually employed for unreplicated experiments, where there are no replicated runs and no dispersion modeling is investigated.

This quantitative analysis is given as follows:

```
==> Response Y[1] : OSCFREQ
    ==> Initial standard error s0 : 5.8724e+05
        Pseudo standard deviation PSE : 3.6619e+05
        Signifiance level alpha : 0.05
        Critical value : 2.0525e+00
    Main Name Accept/Reject Value t(PSE) P-value
Effect
\begin{tabular}{|c|c|c|c|c|c|}
\hline N4 & M (SBSIMP, MUS) & *** PASS & *** & \(9.9816 \mathrm{e}+00\) & 0.001 \\
\hline N27 & M (SBSIMN, U1) & *** PASS & *** & \(9.8368 \mathrm{e}+00\) & 0.001 \\
\hline N21 & M (SBSIMN, MUS) & *** PASS & *** & \(8.9002 \mathrm{e}+00\) & 0.001 \\
\hline N32 & M (SBSIMN, K1) & *** PASS & *** & \(7.6022 e+00\) & 0.001 \\
\hline N15 & M (SBSIMP, K1) & *** PASS & *** & \(5.9861 e+00\) & 0.001 \\
\hline N10 & M (SBSIMP, U1) & *** PASS & *** & \(5.7594 \mathrm{e}+00\) & 0.001 \\
\hline N17 & M (SBSIMP, VFB) & *** PASS & *** & \(4.6422 e+00\) & 0.001 \\
\hline N34 & M (SBSIMN, VFB) & ** PASS & ** & \(4.4348 \mathrm{e}+00\) & 0.002 \\
\hline N18 & M (SBSIMN, X3U1) & *** PASS & *** & \(2.4000 \mathrm{e}+00\) & 0.03 \\
\hline N11 & M (SBSIMP, U0) & *** PASS & * & \(2.1302 \mathrm{e}+00\) & 0.05 \\
\hline N28 & M (SBSIMN, U0) & & & \(1.7737 \mathrm{e}+00\) & 0.09 \\
\hline N31 & M (SBSIMN, K2) & & & \(1.7069 \mathrm{e}+00\) & 0.1 \\
\hline N29 & M (SBSIMN, MUZ) & & & \(1.5284 \mathrm{e}+00\) & 0.2 \\
\hline N1 & M (SBSIMP, X3U1) & & & \(1.5215 \mathrm{e}+00\) & 0.2 \\
\hline N12 & M (SBSIMP, MUZ) & & & \(1.4868 \mathrm{e}+00\) & 0.2 \\
\hline N16 & M (SBSIMP, PHI) & & & \(1.3491 e+00\) & 0.2 \\
\hline
\end{tabular}
```

Non-expert users have only to consider the central column Accept/Reject. Based on our experience, the Lenth's method is not very restrictive. Inactive factors can pass the test. We suggest that misidentifying an inert factor as active should be less important than missing an important and active factor.

## Multi-response Problems

In the case of multi-response problems, a summary of the screening experiments is performed for each response.

```
Active effect(s) for 2 response(s) :
    N4 - M(SBSIMP,MUS) Rank = 33 Response(s) : OSCFREQ ACPOWER
    N27 - M(SBSIMN,U1) Rank = 32 Response(s) : OSCFREQ ACPOWER
    N21 - M(SBSIMN,MUS) Rank = 31 Response(s) : OSCFREQ ACPOWER
    N32 - M(SBSIMN,K1) Rank = 30 Response(s) : OSCFREQ ACPOWER
    N15 - M(SBSIMP,K1) Rank = 29 Response(s) : OSCFREQ ACPOWER
    N10 - M(SBSIMP,U1) Rank = 28 Response(s) : OSCFREQ ACPOWER
    N17 - M(SBSIMP,VFB) Rank = 27 Response(s) : OSCFREQ ACPOWER
    N34 - M(SBSIMN,VFB) Rank = 26 Response(s) : OSCFREQ ACPOWER
    N18 - M(SBSIMN,X3U1) Rank = 25 Response(s) : OSCFREQ ACPOWER
    N11 - M(SBSIMP,U0) Rank = 24 Response(s) : OSCFREQ ACPOWER
    Active effect(s) for 1 response(s) :None
    Unimportant effect(s) detected for all responses:
    N9 - M(SBSIMP,X2MZ)
    N33 - M(SBSIMN,PHI)
    N12 - M(SBSIMP,MUZ)
    N13 - M(SBSIMP,ETA)
    N8 - M(SBSIMP,X2E)
    N3 - M(SBSIMP,X2MS)
```

This global analysis based on the Lenth's method clearly identifies the eight factors m(SBSIM*, MUS), M(SBSIM*, U1), M(SBSIM*, K1), M(SBSIM*,VFB), and the additional M(SBSIMN, X3U1), M(SBSIMP,U0) as active factors.

## Unordered Data Table (CSV Table)

An unordered data table gives the simulation results. These results are stored in a table with the CSV format (Comma Separated Values). CSV is a delimited data format with fields/columns separated by the comma character and records/rows separated by new lines.

## Results of the FIND_FACTOR Process

The FIND_FACTOR option can be used to determine the list of noise parameters prior to any DEX analysis. It will be used to prepare the . paramdex statements. This information can be
found into two different output files: the .dex file contains formatted data, and the include file paramdex.inc file which contains the related .PARAMDEX command.

Consider the following netlist (from the example filter.cir):

```
* CIRCUIT
V1 1 0 DC 0 AC 1
R1 1 2 'R1 + D_R1'
R3 2 0 'R3 + D_R3'
C2 2 INN 'C + D_C'
C3 2 OUT 'C + D_C'
R2 OUT INN 'R2 + D_R2'
Y1 OPAMP1 0 INN OUT 0 PARAM: GAIN='GAIN + D_GAIN' P1='P1 + D_P1'
* DETERMINISTIC PARAMETERS
.PARAM R1 = 159K R2 = 3.18MEG R3 = 79.5
+ C = 1U
+ P1 = 10 GAIN = 10E6
* NOISE PARAMETERS
.PARAM D_R1 = AGAUSS( 0, 10.6K, 1)
.PARAM D_R2 = AGAUSS( 0, 0.212MEG, 1)
.PARAM D_R3 = AGAUSS( 0, 5.30, 1)
.PARAM D_C = AGAUSS( OU, 0.067U, 1)
.PARAM D_P1 = AGAUSS ( 0, 0.667U, 1)
.PARAM D_GAIN = AGAUSS( 0, 0.667E6, 1)
```

By running Eldo with the following .DEX command

```
.DEX
+ EXPERIMENT=SCREENING_NOISE
+ DESIGN=ORTHA_2_N
+ RESPONSE=OPGAIN,OPFREQ,OPBW
+ FIND_FACTOR
```

the .dex file will contain the list of noise parameters as follows:

| Noise | Factor(s) | Dummy Name | Distrib | Nominal Value | Dev/Range |
| :---: | :---: | :---: | :---: | :---: | :---: |
| D_GAIN | SIG=1 | N1 | Gaussian | $0.0000 \mathrm{e}+00$ | $6.6700 e+05$ |
| D_P1 | SIG=1 | N2 | Gaussian | $0.0000 \mathrm{e}+00$ | $6.6700 \mathrm{e}-07$ |
| D_C | SIG=1 | N3 | Gaussian | $0.0000 \mathrm{e}+00$ | $6.7000 \mathrm{e}-08$ |
| D_R3 | SIG=1 | N4 | Gaussian | $0.0000 \mathrm{e}+00$ | $5.3000 \mathrm{e}+00$ |
| D_R2 | SIG=1 | N5 | Gaussian | $0.0000 \mathrm{e}+00$ | $2.1200 \mathrm{e}+05$ |
| D_R1 | SIG=1 | N6 | Gaussian | $0.0000 \mathrm{e}+00$ | $1.0600 \mathrm{e}+04$ |

The following .PARAMDEX command will be found in the file filter_paramdex.inc:

```
.PARAMDEX
+ D_GAIN NOISE/SIG=1.0
```

+ D_C NOISE/SIG=1.0
+ D_R3 NOISE/SIG=1.0
+ D_R2 NOISE/SIG=1.0
+ D_R1 NOISE/SIG=1.0


## The .dex File and the viewdex Script

The .dex file is a structured text file that is organized with sections and sub-sections, and allows the user to skip one or more sections at different levels of detail. The user has to run the service routine named viewdex on the .dex file in order to display the results. This routine can be invoked as follows:
viewdex [-l d] -f file.dex
with the arguments:

- -l d

Where d is the level of detail that users wants to view. The range of levels is 1 to 3 , level 1 (default) gives the least amount of data while level 3 gives the most amount of data.

- Level 1: only the results of the screening experiment are printed for multi and simple response problem.
- Level 2: in the case of multi-responses problem, the results of screening experiments for each response are given separately.
- Level 3: the script gives the ordered and unordered data tables (in CSV format) and the design matrix.

When an outer loop has been performed, the amount of data can be very large. In this case level 1 only reports simplified results in a table printed at the end of the .dex file.

- -f

Name of the .dex file to be formatted.

## .PARAMDEX

The formulation of practical problems requires the consideration of two different types of circuit parameters. To this purpose, the following classification of parameters is proposed:

- deterministic or designable parameters $x$, we will also use the term control parameters;
- statistical or hard to control parameters $s$, we will use the term noise parameters. Usually these parameters are defined in one or several .model statements with the arguments DEv, DEvx and Lот. The levels for these factors are defined as a fraction of the standard deviation (or range) of their probability distribution.

Integrated circuit design features all two types of parameters. The transistor geometries are deterministic design parameters. The transistor model parameters are statistical parameters that reflect inevitable manufacturing fluctuations. On the other hand, in discrete RLC circuits the designable parameters and the statistical variables are in the same space. These notions are explained in details in section "Notes on Statistical Modeling for Discrete Circuits".

When writing the . PARAMDEX statements, the user has to choose the range of the settings for the input factors, and it is wise to give this some thought beforehand rather than just try extreme values. In some cases, extreme values will give runs that are not feasible. Note that these runs are simply ignored during the post-analysis of the experiment.

The actual .Dex command allows for two-level designs that have just "High" and "Low" settings for each factor. The most popular experimental designs are two-level designs. One reason why two is the most common choice is that it is ideal for screening designs, simple and economical; it also gives most of the information required to go to a multilevel response surface experiment if one is needed.

## Command Syntax

The noise factors can be specified with the . Paramdex commands:

```
.PARAMDEX FACTOR_NAME [NOISE/] SIG=NSIGMA
.PARAMDEX FACTOR_NAME [NOISE/] RNG=NRANGE
.PARAMDEX FACTOR_NAME [NOISE/] ABS=DELTA
.PARAMDEX FACTOR_NAME [NOISE/] REL=DELTA%
```

and the designable factors with the following commands:

```
.PARAMDEX FACTOR_NAME [CTRL/] ABS=DELTA [,NOM=RVALUE]
.PARAMDEX FACTOR_NAME [CTRL/] REL=DELTA% [,NOM=RVALUE]
```


## Parameters

- FACTOR_NAME

Name or a reference to a factorial parameter. This parameter can be one of the following:

```
PARAMETER_NAME |
P (PARAMETER_NAME) |
P(SUBCKT_NAME,SUBCKT_PARAMETER_NAME) |
E (DEVICE_NAME,PARAMETER_NAME) |
M(MODEL_NAME,MODEL_PARAMETER_NAME) |
EM(DEVICE_NAME,MODEL_PARAMETER_NAME)
```

These constructs are strongly related to the statical model the user want to define, please consult the section "Selection of Factors for the DEX Analysis" for details. Note that the $\mathbf{P}(.,$.$) construct is not fully implemented in release 2007.1.$

- NOISE, CTRL

This optional argument specifies the category of the factor. Eldo will automatically determine this category, but in order to clarify the netlist it is recommended to write . PARAMDEX commands with these flags.

- SIG=NSIGMA

Fraction of the standard deviation used to define the levels of the factor. The high and low levels are defined with $\pm n \cdot \sigma$ where $\sigma$ is the standard deviation defined on the parameter (see section "Normal and Uniform Distributions" for details).

- RNG=NRANGE

Fraction of the half range used to define the levels of the factor associated to a uniform distribution. The high and low levels are defined with $\pm n \cdot h$ where $h$ is the half range defined on the parameter (see section "Normal and Uniform Distributions" for details).

- ABS=DELTA

The levels are specified with respect to the nominal value $x_{n o m}$ as an absolute perturbation of size $\pm \Delta$.

- REL=DELTA\%

The levels are specified with respect to the nominal value $x_{n o m}$ as a relative perturbation of size $\pm \Delta \cdot x_{\text {nom }}$ (see section "Levels are specified with respect to the nominal value" for details of rel and abs arguments).

- NOM=RVALUE

This argument allows to redefine the nominal value of a designable factor. It is not possible to modify the nominal value of noise factors, since it is part of the user-defined statistical model.

## Two-stage Strategy for the Identification of Critical Factors

A screening experiment is performed to identify the important factors. It is usually referred to as phase zero of a response surface study. The following lines give some guidelines on how screening designs may be conducted.

In the definition of the . PARAMDEX command we began by emphasizing the importance of the control/noise distinction in the statement of IC design. The regression model used in the DEX analysis is defined as follows:

$$
y(x, s)=y_{0}+\sum_{i=1}^{N c} \alpha_{i}\left(x_{i}-x^{0}\right)+\sum_{i=1}^{N n} \beta_{i}\left(s_{i}-s^{0}\right)
$$

The $y_{0}, \alpha$ 's and the $\beta$ 's are a set of unknown coefficients. To estimate the values of these parameters, the DEX analysis collect data on the system we are studying. When no distinction is made among the factors, the $y_{0}, \alpha, \beta$ are estimated within the same experiment. This kind of experiment is only realized when experiment=SCREENING.

We suppose that a two-stage strategy could be used in the case of integrated circuit design, where the designable and noise variables are defined in separate spaces. It may happen that some noise factors, such as environmental noise factors, have large masking effects. The phase zero will then involve two steps:

- a screening experiment for noise factors should be performed first by not considering the designable factors with Experiment=SCREENING_NOISE. The DEX analysis run the experiment by using $x=x^{0}$, where $x^{0}$ is the experiment center in the space of control variables to get the amplitude of the $\beta$ 's;
- by setting experiment=SCREENing_CTri a screening for the control factors would then be launched. The amplitude of the $\alpha$ 's are then analyzed to reduce the list of candidate variables to a relatively few. In this case the noise variables are fixed to their mean value $s^{0}$.


## Noise Factors with DEV and LOT Variations

In statistical models for transistor level simulation, there are two types of variability in device properties, often referred to as inter-die (between chips) and intra-die (within chip) variations. Inter-die variability consists of the accumulated fluctuations of material characteristics form lot-to-lot, wafer-to-wafer and die-to-die (chip-to-chip). However, once the wafers have been cut into individual chips there is no longer a traceable correlation among them. Therefore, lot-to-lot, wafer-to-wafer and die-to-die variations are pooled together into one term: the inter-die variability. This variability equally affects all devices on a given chip. In simulation terms, this means that all devices of a certain type use the same statistical model.

The Eldo simulator allows the specification of two different device-to-device variations. For each run of the sampling algorithm (for instance the Monte Carlo method), the parameters with DEV variations receive a random value each time their symbol is used in expressions. Suppose the following statements:

```
.PARAM param_stat=value DEV=value
.PARAM param1=function_of(param_stat)
.PARAM param2=function_of(param_stat)
.PARAM param3=function_of(param1,param2)
```

The sampling process will compute one value for the parameter param_stat to get the value of param1 and a different random value for param (according to the underlying probability distribution defined on param_stat). Therefore, the expression param3 is a function of two independent statistical parameters, say param1_stat and param2_stat, which share the same probability distribution. In the DEX analysis, a unique factor is defined. This feature comes from two facts:

- the Eldo's extraction language does not allow to make explicit reference to the parameters param1_stat and param2_stat,
- it is always possible to rewrite the expression of param3 as a function of param_stat:
. PARAM param_stat=value DEV=value
.PARAM param3=function_of(param_stat)
It means that the sensitivity of the function param3 with respect to the formal parameter param_stat is not investigated with the parameters param1_stat and param2_stat2 independently.


## Selection of Factors for the DEX Analysis

This section describes how the circuit parameters (the noise and control factors) have to be referenced in the . Paramdex statements. We will consider different situations, but we did not explore all the possibilities. These notes came from our experiments.

We define three statistical parameters, each one has different statistical variations. The global parameter param4_global has no statistical variations.

```
* PARAMETERS DEFINITION
.PARAM param1_global=value DEV=value
+ param2_global=value DEVX=value
+ param3_global=value LOT=value
.PARAM param4_global=value
```

A model MOD1 is defined with two parameters as follows,

```
* MODEL DEFINITION
.MODEL MOD1 ...
+ param1_model=value DEV=value param2_model=value LOT=value . ..
```

and a device named MA,

```
MA ... MOD1 param1_inst=value ... param1_model=value param2_model=value ...
```

We also assumed that the model MOD1 has some instance parameters named param1_inst, and so on.

Suppose that a screening design has to be performed on our formal circuit. The .PARAMDEX statements associated to the model parameters param1_model and param2_model are necessary of the form:

```
.PARAMDEX
+ EM(MA,param1_model) [NOISE/] ...
+ M(MOD1,param2_model) [NOISE/] ...
```

The construct $\mathbf{E m}(.,$.$) always selects a model parameter associated to a specific instance,$ hence it means that this parameter must have DEV or DEVX variations. The second construct $\mathbf{m}(.,$.$) will always be associated to a parameter with LOT variations, since it refers globally to$ a model parameter.

Based on the previous example, we can add a . subckt definition.

```
* SUBCIRCUIT DEFINITION
.SUBCKT CKT1 ... PARAM: param1_ckt=value
.PARAM param1_loc=value
M1 ... MOD1 param1_inst=value ... param1_model=value ...
M2 ... MOD1 param1_inst=value ... param1_model=value ...
R1 ... value
ENDS CKT1
* CIRCUIT
MA ... MOD1 param1_inst=value ... param1_model=value param2_model=value ...
MB ... MOD1 param1_inst=value ... param1_model=value param2_model=value ...
XA ... CKT1 PARAM: param1_ckt=value
XB ... CKT1 PARAM: param1_ckt=value
RA ... function_of(param1_global,...)
```

Suppose we wish to perform a screening experiment on some instances m1, m2, ... with respect to the parameter param1_model and the resistor devices R1 and RA. The following statements

```
.PARAMDEX
+ EM(XA.M1,param1_model) [NOISE/] ...
+ EM(XA.M2,param1_model) [NOISE/] ...
+ EM(XB.M1,param1_model) [NOISE/] ...
```

will select the factors param1_model associated to the instances XA.m1, XA.m2, ..., XB.m1, and so on.

Both the following statements will select the resistor value of the $\mathrm{x} 1 . \mathrm{R1}$ and RA devices.

```
.PARAMDEX
+ E(XA.R1,R) [CTRL/] ...
+ E(RA,R) [CTRL/] ...
```

Note that capacitance and inductance values can also be defined with the selectors $\mathbf{E}(., \mathbf{C})$ and $\mathbf{E}(., \mathbf{L})$ respectively. More generally, instance parameters, such as lengths and widths of transistors, must be also selected with the $\mathbf{E}(.,$.$) construct. For instance, if MOD1 is a$ transistor model, the XA.M1 device will have instance parameters W , L, AD, AS, and so on. These parameters will be selected with E(XA.M1,W), E (XA.M1,L), ... The general syntax is defined as follows:

```
.PARAMDEX
+ E(XA.M1,param1_inst) [CTRL/] ...
+ E(XA.M2,param1_inst) [CTRL/] ...
```

The last selector $\mathbf{P}(.,$.$) allows to manipulate subcircuit parameters. This feature is not$ completely available in the release 2007.1 but we will describe briefly how it is specified to complete these notes.

We are considering this situation:

```
.PARAM param4_global=value
* SUBCIRCUIT DEFINITION
.SUBCKT CKT1 ... PARAM: param1_ckt=value
.PARAM param1_loc=value
M1 ... MOD1 param1_inst=function_of(param4_global) ... param1_model=value ...
M2 ... MOD1 param1_inst=value ... param1_model=value ...
R1 ... value
...
.ENDS CKT1
```

The global parameter param4_global has no random variations. It is therefore a deterministic parameter and can only be selected with these equivalent statements:

```
.PARAMDEX param4_global [CTRL/] ...
.PARAMDEX P(param4_global) [CTRL/] ...
```

The next cases are represented by the explicit and implicit circuit parameters. The parameters param1_ckt and param1_loc can be selected with the $\mathbf{P}(.,$.$) selector.$

```
.PARAMDEX P(XA,param1_loc) [CTRL/] ...
.PARAMDEX P (XA,param1_ckt) [CTRL/] ...
```

Note that the implicit definition of the local parameter param1_loc is not native for the Eldo's language, and should be avoided by the user as much as possible. An explicit definition offers a better understanding.

Now suppose we want to select the factors associated to the global parameters param1_global and param2_global.

* SUBCIRCUIT DEFINITION

```
.SUBCKT CKT1 ... PARAM: param1_ckt=value
M1 ... MOD1 param1_inst=function_of(param1_global,param2_global,...) ...
M2 ... MOD1 param1_inst=function_of(param1_global,param2_global,...) ...
R1 ... value
...
.ENDS CKT1
```

For the parameter param1_global with DEV variations, this list of factor can be large:

```
.PARAMDEX
+ P(XA.M1,param1_global) [NOISE/] ...
+ P(XA.M2,param1,global) [NOISE/] ...
+ P(XB.M1,param1_global) [NOISE/] ...
```

On the other hand, for DEVX variations, the only allowed construct is:

```
.PARAMDEX
+ P(XA,param1_global) [NOISE/] ...
```

since there is only one 'private' parameter attached to each sub-circuit instance.

## Examples

These examples are extracted from the testcase cmos_delay.cir (available in the directory: \$MGC_AMS_HOME/examples/optimizer/). This circuit contains three groups of parameters:

- the process parameters used in a Level 8 NMOS model, such as the Oxide Thickness tox, NMOS Length and Width Reductions (DLn, Dwn), ...
- a second set of environmental noise parameters such as two supply voltages (VPERI, VBB ) and the temperature TP ,
- and the designable variables, the length and width of transistors

Suppose our approach is to assume that process disturbances affect devices within the same chip in the same way: only inter-die variations exist and intra-die variations are negligible. The set of process parameters is common to all NMOS and PMOS devices within the same chip. These statistical definitions can be translated as follows:

```
.PARAM TOX = AGAUSS( 0.015, 0.0003, 1)
+ DL = AGAUSS ( 0.05, 0.0044, 1)
+ DW = AGAUSS ( 1.00, 0.044, 1)
+ VFB = AGAUSS( -0.8632, 0.0186, 1)
```

Then the associated . Paramdex statements could be defined as follows:

```
.PARAMDEX
+ DL NOISE/SIG=2.5
+ DW NOISE/SIG=2.5
+ TOX NOISE/SIG=2.5
+ VFB NOISE/SIG=2.5
```

Note that these statements are equivalent to the following:

```
.PARAMDEX
+ P(DL) NOISE/SIG=2.5
+ P(DW) NOISE/SIG=2.5
+ P(VFB) NOISE/SIG=2.5
+ P(TOX) NOISE/SIG=2.5
```

The next examples illustrate the use of the constructs $\mathbf{m}(.,$.$) and \mathbf{E m}(.,$.$) with the inter and$ intra variations. The use of $\mathbf{m}(.$, ) is not very useful in this case but we will assume that the statistical variations were stated as follows:

```
.PARAM TOX=0.015
.MCMOD NCH TOX LOT/GAUSS=0.0003
.MCMOD PCH TOX LOT/GAUSS=0.0003
```

There are two independent random variables rox associated to the PMOS and NMOS transistor. Two PMOS, or respectively two NMOS, transistors are assumed to be perfectly tracking each other, but PMOS and NMOS transistor have independent variations. This is a very hypothetical situation, since the Oxide Thickness should affect the PMOS and NMOS transistors in the same way. The associated . PARAMDEX command would be as follows,

```
.PARAMDEX
+ M(PCH,TOX) SIG=2.5
+M(NCH,TOX) SIG=2.5
```

Suppose now we are interested in intra-die variations. The statistical variations can be defined as follows:

```
.PARAM TOX=0.015
.MCMOD NCH TOX DEV/GAUSS=0.0003
.MCMOD PCH TOX DEV/GAUSS=0.0003
```

It follows that the associated . PARAMDEX statements are:

```
. PARAMDEX
+ EM(MOPA,TOX) SIG=2.5
+ EM(MIPC,TOX) SIG=2.5
+ EM(MIPA,TOX) SIG=2.5
+ EM(MPNOE,TOX) SIG=2.5
+ EM(MPN4A,TOX) SIG=2.5
+ EM(MPN3A,TOX) SIG=2.5
+ EM(MPN2A,TOX) SIG=2.5
+ EM(MPN1A,TOX) SIG=2.5
+ EM(MONA,TOX) SIG=2.5
+ EM(MINC,TOX) SIG=2.5
+ EM(MINA,TOX) SIG=2.5
+ EM(MNNOD,TOX) SIG=2.5
+ EM(MNN4C,TOX) SIG=2.5
+ EM(MNN4B,TOX) SIG=2.5
```

These statements define a list of independent factors, one for each device. Eldo acts as if private models were created for each device leaving the original model unchanged.

## Notes on Statistical Modeling for Discrete Circuits

An important feature of the Integrated Circuit level models is that the designable parameters, such as widths and lengths of transistors, are deterministic in nature and that they are not in the same space as the noise factors. This property distinguishes IC statistical design from the discrete circuit statistical design as explained below.

Consider the following statements extracted from the example filter.cir (available in the directory: \$MGC_AMS_HOME/examples/optimizer/).

```
V1 1 0 DC 0 AC 1
R1 1 2 'R1 + D_R1'
R3 2 0 'R3 + D_R3'
C2 2 INN 'C + D_C'
C3 2 OUT 'C + D_C'
R2 OUT INN 'R2 + D_R2'
Y1 OPAMP1 0 INN OUT 0 PARAM: GAIN='GAIN + D_GAIN' P1='P1 + D_P1'
```

where the circuit parameters are defined as follows:

```
* DETERMINISTIC PARAMETERS
.PARAM R1 = 159K R2 = 3.18MEG R3 = 79.5
+ C = 1U
+ P1 = 10 GAIN = 10E6
* NOISE PARAMETERS
.PARAM D_R1 = AGAUSS( 0, 10.6K, 1)
.PARAM D_R2 = AGAUSS( 0, 0.212MEG, 1)
.PARAM D_R3 = AGAUSS( 0, 5.30, 1)
.PARAM D_C = AGAUSS( 0, 0.067U, 1)
.PARAM D_P1 = AGAUSS( 0, 0.667U, 1)
.PARAM D_GAIN = AGAUSS( 0, 0.667E6, 1)
```

For the resistors the statistical model is expressed by transformations of the form ' $R+D \_R$ ' where $R$ represents the nominal value and $D \_R$ is the element tolerance or the random variations associated with the control parameter R . These random variables have zero mean. This reflects an important property of discrete RLC circuits that the controllable parameters $x$ and the statistical variables $s$ are in the same space, in other words any circuit performance is a function of random expressions $E\left(x_{i}, s_{i}\right)=x_{i}+s_{i}$.

This property implies that a circuit performance $y(x, s)=y(x+s)$ satisfies the following relation:

$$
\frac{\partial}{\partial x} y(x+s)=\frac{\partial}{\partial s} y(x+s)
$$

The computation of the sensitivity with respect to the designable variables $x$ will be equivalent to the computation of the sensitivity with respect to the tolerances $s$, hence in order to screen
out the important effects the user can safely investigate only the main effects associated to noise factors.

## Notes on Levels Specification

The choice of the levels in the experiment is part of the user's task. In the case of process factors (the noise factors), the . PARAMDEX command is directly related to the statistical data defined in the . PARAM statement. This information is mainly extracted from the arguments of the command:

```
.PARAM PARAMETER_NAME=EXPRESSION
+ {LOT|DEV|DEVX}[/GAUSS|/UNIFORM] = RVALUE|RVALUE%
```

The value EXPR defines the nominal value $x_{n o m}$ or the mean value for the normal and uniform distributions. The value RVALUE represents the standard deviation for the normal distribution and the half-range for the uniform distribution. The following lines review the basic properties of these important distributions and how the data are used in the . PARAMDEX command.

## Caution

In Eldo, the definition of the standard deviation (the $\sigma$ parameter) for the uniform distribution is not correct from the statistical point's of view. A confusion is made between the standard deviation and the range of the distribution. For coherency, the DEX analysis uses the proper definition of this statistical value. This is why the argument SIG and RNG are available for factors associated to uniform distributions.

## Normal and Uniform Distributions

The uniform distribution defines equal probability over a given range for a continuous distribution.

Figure 20-2. Common statistics for $\operatorname{UNIF}(\bar{x}, h)$


The general formula for the probability density function of the uniform distribution is:

$$
f(x)=\frac{1}{U-L}
$$

for $L \leq x \leq U$. The common statistics for the uniform distribution are:

$$
\bar{x}=\frac{U+L}{2}
$$

for the mean, and: $\sigma=\sqrt{\frac{(U-L)^{2}}{12}}$
for the standard deviation. The range of the distribution is the value $U-L$. It means that for the following definition

```
.PARAM PARAMETER_NAME=EXPRESSION {IOT|DEV|DEVX} /UNIFORM=RVALUE|RVALUE%
.PARAM PARAMETER_NAME={AUNIF|UNIF}(EXPRESSION,RVALUE)
```

the value RVALUE, noted $h$ in our formulae, represents half of the range (see Figure 20-2), we will have:

$$
\sigma=\frac{h}{\sqrt{3}} \approx 0.6 \times h
$$

or when this value $h$ is specified as a percentage,

$$
\sigma=\frac{h \times\left|x_{n o m}\right|}{\sqrt{3}}
$$

The general formula for the probability density function of the normal distribution is:

$$
f(x)=\frac{e^{-(\bar{x}-\mu)^{2} /\left(2 \sigma^{2}\right)}}{\sigma \sqrt{2 \pi}}
$$

where the parameters $\bar{x}$, the mean, and $\sigma>0$, the standard deviation, are given.
The user has to note that the macro GAUSS (NOM_VALUE, REL_VALUE, SIG_COEF) allows negative values for the standard deviation SIGMA, since this value is computed as nom_VALUE*REL_VALUE/SIG_COef. It means the nominal value can be negative. The .dex command will only consider the absolute value of these parameters.

The plot in Figure 20-3 depicts the common statistics of the Gaussian distribution.

Figure 20-3. Percentage of cases in eight portions of the Gaussian distribution


It may help the user in defining the levels of a factor associated to such function. For example, the range $[-\sigma, \sigma]$ represents $34.13 \%+34.13 \%=68.26 \%$ of cases obtained after running the sample process in the Monte Carlo algorithm, and the range $[-3 \sigma, 3 \sigma$ ] covers $2(34.13 \%+$ $13.59 \%+2.14 \%)=99.72 \%$ of the cases. It means that the "High" and "Low" levels are the worst case points of the previous ranges.

## Levels as Fraction of the Standard Deviation

This represents a straightforward way to specify levels on noise parameters. The high and low levels are defined with $\pm n \cdot \sigma$ where $\sigma$ is the standard deviation defined on the factor. This situation is depicted in Figure 20-4.

## Figure 20-4. Factor levels $\mathrm{x}_{\text {low }}$ and $\mathrm{x}_{\text {high }}$ for a circuit parameter x



The syntax is defined as follows:
.PARAMDEX FACTOR_NAME [NOISE/] SIG=NSIGMA
Note that it is possible to define levels outside of the range of a uniform distribution, the NSIGMA value may be greater than $\sqrt{3}$, we then may have $x_{\text {high }} \geq U$ and $x_{\text {low }} \leq L$.

This syntax assumes that a uniform or gaussian distribution has been defined on the circuit parameter.

## Levels as Fraction of the Half Range of Uniform Distribution

This option gives the possibility to specify levels on noise parameters associated to uniform distribution. The high and low levels are defined with $\pm n \cdot h$ where $h$ is the half range of the uniform distribution on the factor. The command is as follows
.PARAMDEX FACTOR_NAME [NOISE/] RNG=NRANGE
Note that it is possible to define levels outside of the range of a uniform distribution, the NSIGMA value may be greater than 1.0, we then may have $x_{\text {high }} \geq U$ and $x_{\text {low }} \leq L$.

## Levels are specified with respect to the nominal value

In the cases of noise and control factors, the values of the low level $x_{l o w}$ and high level $x_{\text {high }}$ can be defined explicitly with the following syntaxes:

```
.PARAMDEX FACTOR_NAME [NOISE/] ABS=DELTA
.PARAMDEX FACTOR_NAME [NOISE/] REL=DELTA%
.PARAMDEX FACTOR_NAME [CTRL/] ABS=DELTA [NOM=RVALUE]
.PARAMDEX FACTOR_NAME [CTRL/] REL=DELTA% [NOM=RVALUE]
```

For instance, the low level is $x_{\text {low }}=x_{\text {nom }}-\Delta$ and $x_{\text {low }}=(1-\Delta) \cdot x_{\text {nom }}$ for each type of design factors, and the high level is defined similarly by $x_{\text {low }}=x_{\text {nom }}+\Delta$ and $x_{\text {high }}=(1+\Delta) \cdot x_{\text {nom }}$, where $x_{\text {nom }}$ is the nominal value. It is possible to specify a value for the nominal value of a control parameter. This is done with the argument nom=RVALUE.

## Examples of Experimental Design

The following table gives a brief description of the basic examples used. These circuits are available in the directory: \$MGC_AMS_HOME/examples/optimizer/

| Example | File name | Description |
| :--- | :--- | :--- |
| Passive band pass filter | bpass.cir | Basic discrete RLC circuit |
| Active band pass filter | filter.cir | Another discrete circuit |
| CMOS delay circuit | cmos_delay.cir | Basic example with BSIM1 models |
| CMOS ring oscillator | cmos_ring.cir | Another example with BSIM1 models |
| 8-bit CMOS ripple <br> carry adder | adder.cir | Yet another example with BSIM1 models |

## References

1. C. F. Jeff Wu, Michael Hamada. Experiments: Planning, Analysis, and Parameter Design Optimization. John Wiley \& Sons, 2000.
2. Hedayat, A. and Wallis W.D. Hadamard Matrices and Their Applications. Annals of Statistics, Vol. 6, No. 6 (Nov., 1978), pp. 1184-1238.

## Chapter 21 <br> Reliability Simulation

## Introduction

Reliability models have been implemented in Eldo's UDRM interface (User Defined Reliability Model).

The objective of reliability simulation is to be able to model the gradual damage, which occurs to the devices in a certain design causing degradation in the performance of that design. It is required to evaluate the amount of degradation occurring in a certain period of operation and examine the circuit performance after this period. The modeled damage could follow one or more of several damage mechanisms, which show gradual degradation in device performance. Other mechanisms, which cause sudden and complete damage of the device, (like the oxide breakdown for example) are not targeted in this scope.

The reliability simulations follows the model defined by the user using the UDRM interface. A simple Hot-carrier and NBTI reliability model is provided as an example.

Please refer to Eldo UDRM User's Manual for more information.

## Running Reliability Simulation in Eldo

Reliability simulation in Eldo can be used with any normal netlist provided that it contains a . TRAN analysis. This . TRAN analysis will be the analysis used for all the fresh and aged simulations, and its outputs will be available also for all the fresh and aged simulations. The reliability simulation can be invoked and controlled through the Eldo reliability commands.

The reliability commands are detailed in the Eldo UDRM User's Manual, and summarized in Table 21-1.

Table 21-1. Eldo Reliability Commands

| Command | Description |
| :--- | :--- |
| .AGE | Age analysis |
| .AGE_LIB | Define functions for reliability |
| .AGEMODEL | Reliability model parameter declaration |
| .SETKEY | Set reliability model key (password) |
| .USEKEY | Use reliability model key (password) |

Reliability Simulation
Running Reliability Simulation in Eldo

# Chapter 22 <br> Post-Processing Library 

## Introduction

The Post-Processing Library (PPL) is a tool that allows interfacing between Eldo and a set of predefined, user defined DSP or mathematical functions. User Defined Functions (UDF) are written using the scripting language Tcl. This chapter describes both the commands used from Eldo to call a PPL function and the extensions of the Tcl language for Post-Processing abilities.

A number of example files are provided to illustrate as many configurations as possible, see "Example Files" on page 1260.

## General Usage

## Registering User Defined Functions inside Eldo

## Use Tcl File

```
.USE_TCL FILENAME
```

The . USE_tcl command (see ".USE_TCL" on page 929) loads the Tcl file, filename, into the Eldo Tcl interpreter, making all declared functions to be recognized inside Eldo. Since these functions will have to be identified during the parsing of the netlist, the .USE_TCL commands must be placed before any call to one of these functions.

After loading the Tcl file, Eldo can use all the functions written in this file as if they were macros. This means that these functions can accept any argument, are defined for the whole netlist, and can return both numbers and/or waves.

## Macro-Like Usage of UDF

The following example shows how two resistors get their values directly from a UDF function or through a parameter (the files are realvalue.cir and realvalue.tcl). See "Example Files" on page 1260 for descriptions and information on where to find these and other example files.

File realvalue.tcl listing:

```
# Function which returns a real value
    proc GETVALUE { rname rval } {
# Use native Tcl syntax for expression calculation
```

```
    set newvalue [expr 2*$rval + log($rval)]
puts "The value of resistor $rname is $newvalue"
return $newvalue
}
```


## Note

The name of the function must be in uppercase, or Eldo will not be able to identify it.

File realvalue.cir listing:

```
* This example demonstrates the use of a simple Tcl function
* returning a real value
* use_tcl commands must always be put before the first call
* to a Tcl function. Otherwise, Eldo will not be able to parse
* the expressions using these functions
.use_tcl realvalue.tcl
.param p1={GETVALUE("R1",TEMPER) }
.param p2=1
v1 1 0 sin(0 2 1g)
r1 1 2 p1
r2 2 0 {GETVALUE("R2",p2)}
.tran 1n 10n
.plot tran i(r1)
.end
```

Except for the dump of the value, the Tcl function getvalue is equivalent to:

```
.defmac GETVALUE(val) = 2*val+log(val)
```

UDF parameters can be real values, strings, waves, macros, UDF or keywords (see "Keyword Parameters" on page 1256). It is important to note that for this kind of use, the UDF may be called for each timestep. Thus wave parameters are not passed to the UDF as objects but as real values.

The example files samphold.cir and samphold.tcl (see "Example Files" on page 1260) contain another example of UDF. The function uses a Tcl namespace to keep the previous value of a wave, and is called inside a .DEFWAVE to create a sampled representation of the input wave.

## Keyword Parameters

The following keywords can be used in any calls to UDF:

## XAXIS / TIME / FREQ Specifies the current timestamp or frequency

TEMPER
specifies the current temperature

The following keywords can only be used in .CALL_TCL commands:

| ICARLO | specifies the current index of Monte-Carlo run |
| :--- | :--- |
| IRUN | specifies the current step index |
| IALTER | specifies the current alter index |
| NBCARLO | specifies the number of Monte-Carlo run |
| NBRUN | specifies the number of step |
| NBALTER | specifies the number of .ALTER statements |

## Making Specific Calls to UDF inside Eldo

The CALL_TCL command is used to perform a single call to a Tcl function. For details on this command see ".CALL_TCL" on page 559. The example files (see "Example Files" on page 1260) expressions.cir and expressions.tcl demonstrate how .CALL_TCL can be used.

## Working with Waveforms inside UDF

## Waveforms in Arguments

It is very important to note that in the context of .CALL_TCL commands, waves are not real values but vectors, or, in a more general way, objects are generated by Eldo and given to the PPL. The argument that UDF receives is only a reference to an object. Thus it is impossible to use directly these references in mathematical expressions such as:

```
proc WAVE_PLUS { wv_in } {set wv_out [expr $wv_in + $wv_in]
+ return $wv_out}
```


## Waveforms in Expressions

To allow operations on waveforms, a set of commands has been registered inside the PPL environment. The following table lists common operators' syntax and the equivalent syntax used inside the PPL.

Table 22-1. C and PPL Syntax

| C Syntax | C Example | PPL Syntax | PPL Example |
| :--- | :--- | :--- | :--- |
| + | $\mathrm{a}=\mathrm{b}+\mathrm{c}$ | add | set a [add \$b \$c] |
| - | $\mathrm{a}=\mathrm{b}-\mathrm{c}$ | sub | set a [sub \$b \$c] |
| $*$ | $\mathrm{a}=\mathrm{b} * \mathrm{c}$ | mult | set a [mult \$b \$c] |
| $/$ | $\mathrm{a}=\mathrm{b} / \mathrm{c}$ | div | set $\mathrm{a}[$ div \$b \$c] |
| $\wedge$ | $\mathrm{a}=\mathrm{b} \wedge \mathrm{c}$ | pow | set a [pow \$b \$c] |

Table 22-1. C and PPL Syntax

| C Syntax | C Example | PPL Syntax | PPL Example |
| :--- | :--- | :--- | :--- |
| fmod | $\mathrm{a}=\mathrm{fmod}(\mathrm{b}, \mathrm{c})$ | $\bmod$ | set a $[\bmod \$ \mathrm{~b} \$ \mathrm{c}]$ |

These commands accept real, complex and/or wave arguments. For example, it is possible to add two waveforms, a waveform and a real, or two reals.

Looking more closely at the Tcl syntax, it is obvious that complex expressions can be very difficult to read.

For example, in common language:
$a=((b+c) *(d+e)) /(f+g)$
becomes, in Tcl:

```
set a [div [mult [add $b $c] [add $d $e]] [add $f $g]]
```

Two commands have been defined to simplify the syntax, evalexpr (see evalExpr) and defineVec (see defineVec).

The example files, expressions.cir and expressions.tcl, show the two different syntaxes. See "Example Files" on page 1260 for more information on example files.

## evalExpr

## Syntax

evalExpr expression

## Description

Evaluates an expression in C-Like syntax. The evalExpr command allows evaluation of an expression written using C-like syntax. It can contain both numbers and/or waves with quotes being mandatory. If the expression is purely numerical a single value is returned. Otherwise the result is a vector and is printed using the display command format (display command and output will be described later).

This command is more likely to be used with numerical expressions whereas the defineVec command (see "defineVec" on page 1260) is for wave calculations.

## Example

```
proc EVAL_EXPR { wv_in } {
    set a 3
    set numerical [evalExpr "2*$a + 4"]
    puts "numerical = $numerical"
    set vector [evalExpr "2*$wv_in + 4"]
    puts "vector = $vector"
}
```

A call to this function from Eldo command:

```
.call_tcl tran where=END eval_expr(v(1))
```

produces the following output:

```
numerical = 10.00000000000000
vector = { 0 0.00000000000000 4.000000000000000 +
0.00000000000000j }
    {1 0.00000000002000 4.50133293425722 + 0.00000000000000j }
    {2 0.00000000003900 4.97030313987119 + 0.00000000000000j }
    {3 0.00000000007699 5.86034757905359 + 0.00000000000000j }
    {4 0.00000000015297 7.27942102760290 + 0.00000000000000j }
    { 5 0.00000000022966 7.96738275669581 + 0.00000000000000j }
    {6 0.00000000025000 8.00000000000000 + 0.00000000000000j }
    { 7 0.00000000029068 7.87006296906364 + 0.00000000000000j }
    { 8 0.00000000035325 7.18743864881722 + 0.00000000000000j }
```


## defineVec

## Syntax

defineVec <output_object> expression

## Description

Defines a PPL object using C-Like syntax. Like the evalExpr command (see "evalExpr" on page 1259), defineVec allows evaluation of an expression written using C-like syntax but the result is stored in a PPL object named <output_object> rather than displayed. An error occurs if an object using the same name already exists in the PPL.

This command is more likely to be used with wave calculations, whereas the evalExpr command is for numerical expressions.

## Example

```
proc DEFINE_EXPR { wv_in } {
    set a 3
    defineVec numerical "2*$a+4"
    puts "numerical = [display numerical]"
    defineVec vector "$wv_in+4"
    puts "vector = [display vector]"
    return vector
}
```

A call to this function from the Eldo command:

```
.call_tcl tran where=END define_expr(v(1))
```

produces the same output as evalexpr but the object vector can be reused in any expression or returned to Eldo in order to be dumped in the output file.

## Caution

It is very important to note that the return value of this function is not a Tcl variable but directly vector.

## Example Files

The following example files are provided in your installed directory:
\$MGC_AMS_HOME/examples/ppl

- realvalue.cir and realvalue.tcl
demonstrates how to use UDF in a macro-like way to define a resistor value.
- samphold.cir and samphold.tcl
demonstrates how to use UDF in a macro-like way to define defwaves, and namespace in Tcl .
- expressions.cir and expressions.tcl
demonstrates how to use .CALL_TCL commands and how to work with expressions inside the UDF.
- tcl_wave.cir and expressions.tcl
demonstrates how to use the .TCL_WAVE command.
- wave_info.cir and wave_info.tcl
demonstrates how to use wave informations commands and loops in Tcl.
- wave_meas.cir and wave_meas.tcl
demonstrates how to use measurement functions in UDF.
- asciigen.cir and asciigen.tcl
demonstrates how to use several .CALL_TCL commands to dump waves in an ASCII output file.


## Built-In Waveform Functions

Table 22-2. Built-In Waveform Functions

| Eldo Functions |  |  |  |  |
| :--- | :--- | :--- | :--- | :--- |
| ABS | ACOS | ACOSH | ACOT | ACOTH |
| ASIN | ASINH | ATAN | ATANH | AVG |
| COS | COSH | COT | COTH | DB |
| DEG | DELAY | DERIVE | DRV | EXP |
| FALLTIME | GMARGIN | HISTOGRAM | IMAG | INTEG |
| INTEGRAL | INTERSECT | INVDB | LOG | LOG10 |
| MAG | MAX | MIN | PHASE | PHMARGIN |
| RAD | REAL | RELATION | RISETIME | RMS |
| SAMPLE | SETTLINGTIME | SIN | SINH | SQR |
| SQRT | SUM | TAN | TANH | VMAX |
| VMIN | WINDOW | XVAL | XWAVE | YVAL |

Table 22-2. Built-In Waveform Functions

| Eldo RF Functions |  |  |  |  |
| :--- | :--- | :--- | :--- | :--- |
| COMPRESS | IIPXIIPX | OIPX | TPD | TPDDD |
| TPDDU | TPDUDTPDUD | TPDUU | XCOMPRESS |  |

In the following descriptions, the syntax is shown immediately after the function name, then a short description, then, if applicable, descriptions of the arguments. wv_in is the input waveform the function is acting upon. wv_out is the resulting output waveform.

## Eldo Functions

```
ABS
set wv_out [abs $wv_in]
```

Absolute wave.

## ACOS

set wv_out [acos \$wv_in]
Inverse trigonometric wave function.

## ACOSH

set $w v$ _out [acosh \$wv_in]
Inverse hyperbolic wave function.

```
ACOT
    set wv_out [acot $wv_in]
```

Inverse trigonometric wave function.

## ACOTH

set wv_out [acoth \$wv_in]
Inverse hyperbolic wave function.
ASIN
set wv_out [asin \$wv_in]
Inverse trigonometric wave function.
ASINH
set wv_out [asinh \$wv_in]
Inverse hyperbolic wave function.

ATAN
set wv_out [atan \$wv_in]
Inverse trigonometric wave function.

## ATANH

set wv_out [atanh \$wv_in]
Inverse hyperbolic wave function.
AVG

```
set out_value [avg $wv_in]
set out_value [avg $wv_in $lower_bound $upper_bound]
```

Average value of a wave.

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops
COS
set wv_out [cos \$wv_in]
Trigonometric wave function.


## COSH

set wv_out [cosh \$wv_in]
Hyperbolic wave function.
COT
set wv_out [cot \$wv_in]
Trigonometric wave function.
COTH
set wv_out [coth \$wv_in]
Hyperbolic wave function.
DB
set wv_out [db \$wv_in]
Conversion dB magnitude. See also INVDB.

## DEG

```
set wv_out [deg $wv_in]
```

Conversion degrees. See also RAD.

## DELAY

set wv_out [delay \$wv_in \$delay_value]
Creates a delayed wave.

## DERIVE

set out_value [derive \$wv_in \$xvalue]
Derivative of a wave at an $x$ value.
DRV
set wv_out [drv \$wv_in]
Derivative of a wave with respect to the $x$ (or scale) variable.

## EXP

set wv_out [exp \$wv_in]
Wave exponential.

## FALLTIME

set out_value [falltime \$wv_in \$lower_thr \$upper_thr]
set out_value [falltime \$wv_in \$lower_thr \$upper_thr \$after]
Fall time of a wave, the result is of unit $\left\{x \_u n i t\right\}$.

- lower_thr

Lower threshold.

- upper_thr

Upper threshold.

- after

First transition between lower and upper thresholds is treated after this x value.

## GMARGIN

set out_value [gmargin \$wv_in1 \$wv_in2]
Gain margin is the linear gain distance to 1.0. See gain margin extraction example.

## HISTOGRAM

set wv_out [histogram \$wv_in \$intervals]

```
set wv_out [histogram $wv_in $intervals $sample]
set wv_out [histogram $wv_in $intervals $lower_bound $upper_bound]
set wv_out [histogram $wv_in $intervals $lower_bound $upper_bound $sample]
```

Generates a histogram of the input wave showing the waves magnitude probability density distribution. The input wave is first sampled to equidistant points if the optional argument <\$sample> is set.

- intervals
the number of histogram intervals
- sample
if 0 or not specified: don't sample
- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops


## IMAG

set wv_out [imag \$wv_in]
Imaginary part of a magnitude and phasewave pair (magnitude: linear, phase: in degrees). See also REAL.

## INTEG

set out_value [integ \$wv_in]
set out_value [integ \$wv_in \$lower_bound \$upper_bound]
Definite integral of the input wave with respect to the x (or scale) variable, global integral or interval integral the result has the unit $\{$ wave_unit $\} *\left\{x \_u n i t\right\}$.

- lower_bound
x value after which measurement starts
- upper_bound
$x$ value after which measurement stops


## INTEGRAL

set $W v$ _out [integral $\left.\$ w v \_i n ~ \$ f i r s t \_y \_v a l u e\right]$
Indefinite integral of the input wave with respect to the x -axis variable. The result is a waveform.

- first_y_value

Integration constant

## INTERSECT

```
set out_vector [intersect $wv_in1 $wv_in2]
set out_vector [intersect $wv_in1 $wv_in2 $lower_bound $upper_bound]
```

Get the intersection point (s) of two waves.

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops


## INVDB

set wv_out [invdb \$wv_in]
Conversion linear magnitude. See also DB.

## LOG

set wv_out [log \$wv_in]
Wave logarithm.
LOG10
set wv_out [log10 \$wv_in]
Wave logarithm.
MAG
set wv_out [mag \$wv_in]
Linear magnitude from real and imaginary part.
MAX
set wv_out [max \$wv_in1 \$wv_in2]
Maximum wave of two waves (max is evaluated point-by-point).
MIN
set wv_out [min \$wv_in1 \$wv_in2]
Minimum wave of two waves (min is evaluated point-by-point).

## PHASE

set wv_out [phase \$wv_in]
Phase (in degrees) from real and imaginary part.

## PHMARGIN

```
    set out_value [phmargin $wv_in1 $wv_in2]
```

Phase margin is the phase distance to -180 degrees. See phase margin extraction example.

```
RAD
    set wv_out [rad $wv_in]
```

Conversion radians. See also DEG.

## REAL

```
set wv_out [real $wv_in]
```

Real part of a magnitude and phasewave pair (magnitude: linear, phase: in degrees). See also IMAG.

## RELATION

```
set wv_out [relation $wv_in1 $wv_in2 $operator]
```

Generates a wave from the point-by-point comparison of two waves. It returns 1 whenever operator is 1 and wv_in1 > wv_in2, or operator is 0 and wv_in1 == wv_in2, or operator is -1 and wv_in1 < wv_in2. Otherwise it returns 0 .

## RISETIME

```
set out_value [risetime $wv_in $lower_thr $upper_thr]
set out_value [risetime $wv_in $lower_thr $upper_thr $after]
```

Rise time of a wave, the result is of unit $\left\{x_{-}\right.$unit $\}$.

- lower_thr

Lower threshold.

- upper_thr

Upper threshold.

- after

First transition between lower and upper thresholds is treated after this x value.

## RMS

```
rms=sqrt ((1/ (x_max-x_min))*integ(wave^2)).
set out_value [rms $wv_in]
set out_value [rms $wv_in $lower_bound $upper_bound]
```

Root mean square value of a wave.

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops


## SAMPLE

set wv_out [sample \$wv_in \$sample_time]
set wv_out [sample \$wv_in \$sample_time \$lower_bound \$upper_bound \$sample]

Creates a sampled wave.

- sample_time
sampling period
- lower_bound
x value after which sampling starts
- upper_bound
x value after which sampling stops


## SETTLINGTIME

set out_value [settlingtime \$wv_in \$yvalue \$eps]
set out_value [settlingtime \$wv_in \$yvalue \$eps \$lower_bound \$upper_bound]
Time required for the input wave to settle within a certain limit around the final value.

- yvalue

Value to reach.

- eps

Tolerance value (yvalue $+/-\mathrm{eps} / 2$ ).

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops
SIN
set wv_out [sin \$wv_in]
Trigonometric wave function.


## SINH

set wv_out [sinh \$wv_in]
Hyperbolic wave function.

SQR

```
set wv_out [sqr $wv_in]
```

Wave square.
SQRT
set wv_out [sqrt \$wv_in]
Wave square root.
SUM

```
set out_value [sum $wv_in]
set out_value [sum $wv_in $lower_bound $upper_bound]
```

Sums up the real part of a vector.

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops
TAN
set wv_out [tan \$wv_in]
Trigonometric wave function.


## TANH

set wv_out [tanh \$wv_in]
Hyperbolic wave function.

## VMAX

set out_value [vmax \$wv_in]
set out_value [vamx \$wv_in \$lower_bound \$upper_bound]
Maximum value of a wave.

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops

```
VMIN
    set out_value [vmin $wv_in]
    set out_value [vmin $wv_in $lower_bound $upper_bound]
```

Minimum value of a wave.

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops


## WINDOW

```
set wv_out [window $wv_in $lower_bound $upper_bound]
```

Selects a window ( $a, b$ ) out of a wave, the points at the interval bounds are interpolated.

- lower_bound, upper_bound

Begin and end of the wave window to select.
XVAL

```
set out_vector [xval $wv_in $yvalue]
set out_vector [xval $wv_in $yvalue $slope]
set out_vector [xval $wv_in $yvalue $slope $lower_bound $upper_bound]
```

All x (or scale) values for one wave (or y) value.

- slope

Find only $x$ values, where wave crosses y with slope:
slope > 0 Positive slope
slope < 0 Negative slope
slope $=0$ Positive and negative slope

- lower_bound
x value after which measurement starts
- upper_bound
x value after which measurement stops


## XWAVE

set wv_out [xwave \$Wv_in]
Creates a wave with $\mathrm{y}=\mathrm{x}$ values.

## YVAL

set out_value [yval \$wv_in \$xvalue]
Wave value at x (or scale) value (linear interpolation to get the exact value).

## RF Functions

## COMPRESS

```
set out_value [compress $wv_in $val]
```

Extracts the Y-axis value of the wave at the point where the difference between the actual value of the wave and the linear extrapolation of the wave based on the computed slope value becomes greater than val.

## IIPX

```
set out_value [iipx $wv_in $wave_out $freq1 $freq2]
```

Returns the input referred intercept point of order $x$ from the value of the circuit input and output, wv_in and wave_out respectively. wv_in and wave_out must be in dB or dBm. The intercept order is directly calculated from the inter modulation of freq1 and freq2.

## OIPX

```
set out_value [oipx $wv_in $freq1 $freq2]
```

Returns the output referred intercept point of order $x$ from the value of the circuit output wave, this must be in dB or dBm . The intercept order is directly calculated from the inter modulation of freq 1 and freq2.

TPD

```
set out_value [tpd $wv_in1 $wv_in2]
set out_value [tpd $wv_in1 $wv_in2 $vth]
set out_value [tpd $wv_in1 $wv_in2 $vthin $vthout]
set out_value [tpd $wv_in1 $wv_in2 $vthin $vthout $before $after]
set out_value [tpd $wv_in1 $wv_in2 $vthin $vthout $before $after $occur]
```

Returns the propagation delay between wv_in1 and wv_in2.

## Note

For a complete description of TPD and its parameters, see ".EXTRACT" on page 637.

- vth

Voltage defining a threshold or starting point.

- vthin

Voltage defining a threshold or starting point.

- vthout

Voltage defining a threshold or starting point.

- before

Causes the function to be performed only if TIME<val .

- after

Causes the function to be performed only if TIME $>$ val .

- occur

Computes the function for the VALth occurrence of the event.

## TPDDD

Returns the propagation delay(TPD) with WAVE1 and WAVE2 both falling.

## TPDDU

Returns the propagation delay(TPD) with WAVE1 falling, WAVE2 rising.

## TPDUD

Returns the propagation delay(TPD) with WAVE1 rising, WAVE2 falling.

## TPDUU

Returns the propagation delay(TPD) with WAVE1 and WAVE2 both rising.

## XCOMPRESS

set out_value [xcompress \$wv_in \$val]
Extracts the X -axis value of the wave at the point where the difference between the actual value of the wave and the linear extrapolation of the wave based on the computed slope value becomes greater than val.

## Built-In DSP Functions

Table 22-3. Built-In DSP Functions

| AUTOCOR | CONV | CORRELO | CT | FFT |
| :--- | :--- | :--- | :--- | :--- |
| HARMONICS | HDIST | IFFT | PERIODO | PSD |
| SAMPLER | SNR |  |  |  |

In the following descriptions, the syntax is shown immediately after the function name, then a short description, then, if applicable, descriptions of the arguments.

## AUTOCOR

set wv_out [autocor \$wv_in \$method]
set wv_out [autocor \$wv_in \$method \$nbpts]
Calculates the Auto Correlation Function (AF) of a waveform.

The AF of a signal waveform is an average measure of its time domain properties and therefore especially relevant when the signal is random.

There are two methods available for calculating the auto correlation, namely the Correlogram and Periodogram methods.

For more explanation refer to the EZwave User's Manual.

- method

Select the AF calculation method.
0 for correlogram (default)

## 1 for periodogram

- nbpts

Number of points for the AF result.

## CONV

set wv_out [conv \$wv_in1 \$wv_in2 \$nptsa \$nptsb \$fs]
Calculates the convolution of two signals. For more explanation refer to the EZwave User's Manual.

- nptsa

Number of points for wave1.

- nptsb

Number of points for wave2.

- fs

Sampling Frequency.

## CORRELO

```
set wv_out [correlo $wv_in $tstart $tstop $fs $nbpts $padding
+ $sample $fmin $fmax $normalized $ncor $nauto $npsd]
```

Calculates the Power Spectral Density using correlogram method. For more explanation refer to the EZwave User's Manual.

- tstart

Start time for the signal.

- tstop

Stop time for the signal.

- fs

Sampling frequency.

- nbpts

Number of sampling points.

- padding

Selects the padding zeros type:
0 No Padding
1 Padding at the end
2 Padding at the start
3 Center wave

- sample

Selects the sampling type:
0 No sampling
1 Interpolation
2 Sample and Hold

- fmin

Starting frequency used inside the FFT result window.

- fmax

Last frequency used inside the FFT result window.

- normalized

0 No normalization
1 All real and imaginary parts of the result are divided by $\mathrm{Nbpts} / 2$ except for the first point, which is divided by Nbpts.

- ncor

Number of auto correlation points used for the PSD computation. Default value is Nauto.

- nauto

Number of points for the auto correlation result. Default value is Nbpts. Necessary condition is Nauto $2>=2$

- npsd

Number of points for the PSD result. Default value is Ncorr/2+1. Necessary condition is npsd $>=$ Ncorr $/ 2+1$.

CT
 \$fmax \$normalized \$nzoom]

Calculates the Chirp Transformed (CT) wave. For more explanation refer to the EZwave User's Manual.

- tstart

Start time for the signal.

- tstop

Stop time for the signal.

- fs

Sampling frequency.

- nbpts

Number of sampling points.

- padding

Selects the padding zeros type:
0 No Padding
1 Padding at the end
2 Padding at the start
3 Center wave

- sample

Selects the sampling type:
0 No sampling
1 Interpolation
2 Sample and Hold

- fmin

Starting frequency used inside the FFT result window.

- fmax

Last frequency used inside the FFT result window.

- normalized

0 No normalization
1 All real and imaginary parts of the result are divided by $\mathrm{Nbpts} / 2$ except for the first point, which is divided by Nbpts.

- nzoom

Number of points for the zooming.

## FFT

set $w v$ _out $[f f t$ \$tstart $\$ t s t o p$ \$fs \$nbpts \$padding \$sample \$fmin \$fmax \$normalized]

Calculates the Fast Fourier Transform (FFT) of a wave. FFT is the fastest and most efficient available algorithm for computing the DFT.

- tstart

Start time for the signal.

- tstop

Stop time for the signal.

- fs

Sampling frequency.

- nbpts

Number of sampling points.

- padding

Selects the padding zeros type:
0 No Padding
1 Padding at the end
2 Padding at the start
3 Center wave

- sample

Selects the sampling type:
0 No sampling
1 Interpolation
2 Sample and Hold

- fmin

Starting frequency used inside the FFT result window.

- fmax

Last frequency used inside the FFT result window.

- normalized

0 No normalization
1 All real and imaginary parts of the result are divided by $\mathrm{Nbpts} / 2$ except for the first point, which is divided by Nbpts.

## HARMONICS

set wv_out [harmonics \$wv_in \$fundf]
set wv_out [harmonics \$wv_in \$fundf \$fmin \$fmax]
Calculates harmonics inside the interval [fmin, fmax] then generates the harmonics wave.

- fundf

Fundamental Frequency.

- fmin, fmax
frequency band that should be taken for the computation.


## HDIST

```
set out_value [hdist $wv_in $fundf]
set out_value [hdist $wv_in $fundf $fmin $fmax]
```

Calculates the Total Harmonic Distortion (THD) of a signal.

- fundf

Fundamental frequency.

- fmin, fmax

Frequency band that should be taken for the computation.

## IFFT

set wv_out [ifft \$wv_in]
Calculates the Inverse Fast Fourier Transform.

## PERIODO

set $W v$ _out [periodo \$wv_in \$tstart \$tstop \$fs \$nbpts \$padding

+ \$sample $\$ f m i n$ \$fmax $\$ n o r m a l i z e d ~ \$ n c o r ~ \$ n a u t o ~ \$ n p s d] ~$
Calculates the Power Spectral Density using periodogram method. For more explanation refer to the EZwave User's Manual.
- tstart

Start time for the signal.

- tstop

Stop time for the signal.

- fs

Sampling frequency.

- nbpts

Number of sampling points.

- padding

Selects the padding zeros type:
0 No Padding
1 Padding at the end
2 Padding at the start
3 Center wave

- sample

Selects the sampling type:
0 No sampling
1 Interpolation
2 Sample and Hold

- fmin

Starting frequency used inside the FFT result window.

- fmax

Last frequency used inside the FFT result window.

- normalized

0 No normalization
1 All real and imaginary parts of the result are divided by $\mathrm{Nbpts} / 2$ except for the first point, which is divided by Nbpts.

- ncor

Number of auto correlation points used for the PSD computation. Default value is Nauto.

- nauto

Number of points for the auto correlation result. Default value is Nbpts. Necessary condition is Nauto $2>=2$

- npsd

Number of points for the PSD result. Default value is Ncorr/2 + 1. Necessary condition is npsd $>=$ Ncorr $/ 2+1$.

PSD
set wv_out [psd \$wv_in \$method]
set wv_out [psd \$wv_in \$method \$nbpts]
Calculates the Power Spectral Density (PSD) of a waveform.
The PSD of a signal waveform is an average measure of its time domain properties and therefore especially relevant when the signal is random.

There are two methods available for calculating the PSD, namely the Correlogram and Periodogram methods.

For more explanation refer to the EZwave User's Manual.

- method

Select the PSD calculation method.
0 for correlogram (default)

1 for periodogram

- nbpts

Number of points for the PSD result.

## SAMPLER

set wv_out [sampler \$tstart \$tstop \$fs \$nbpts \$padding \$wtype \$wparam]
Generates a sampled wave using some types of windowing.

- tstart

Start time for the signal.

- tstop

Last time for the signal.

- fs

Sampling frequency.

- Nbpts

Number of sampling points.

- padding

Selects the padding zeros type:
0 No Padding
1 Padding at the end
2 Padding at the start
3 Center wave

- wtype

Window type:
0 Rectangular (no wparam)
1 Hamming (no wparam)
2 Hanning (Alpha= w_param, default is 0.5)
3 Parzen (no wparam)
4 Welch (no wparam)
5 Blackman (no wparam)
6 Blackman7 (no wparam)
7 Bartlett (no wparam)
8 Kaiser (Beta= wparam, default is 10.056 )
9 Klein (no wparam)

10 Tukey (no wparam)
11 Dolph Chebyshev (Alpha=w_param, default: 3.0)

- wparam

Window optional parameter.

## SNR

set out_value [snr \$wv_in \$fmin \$fmax \$freq_list]
Calculates the Signal to Noise Ratio in dBs of a noisy wave by using a specific frequency list.

- fmin, fmax

Frequency band that should be taken for the computation.

- freq_list

List of frequencies which should be used in the computation.

## Accessing Waves Inside an External Database

In the following descriptions, the syntax is shown immediately after the function name, then a short description, then, if applicable, descriptions of the arguments.

## LOAD_FILE <br> load_file \$filename

Loads a cou file in memory. This command returns a list of run identifiers. These identifiers are labelled Run X where X is an absolute counter starting from 0 .

## Examples

If a file test.cou contains one run:

```
puts "[load_file test.cou]"
```

Implies "Run0" will be used as the run identifier label.
If a file test $2 . c o u$ contains three runs:
puts "[load_file test2.cou]"
Implies "Run0 Run1 Run2" will be used as the run identifier labels.
If both commands are called in the same UDF:

```
puts "[load_file test.cou]"
```

Implies "Run0" will be used as the run identifier label.

```
puts "[load_file test2.cou]"
```

Implies "Run1 Run2 Run3" will be used as the run identifier labels.

These identifiers are used to identify waves. For example if file test.cou contains waves $v(1)$ and $\mathrm{i}(\mathrm{r} 1)$, their internal names inside the PPL will be Run0::v(1) and Run0::i(r1). These names can be used in all expressions.

## DISP_FILE

```
disp_file
disp_file $identifier
```

Displays the list of runs inside the PPL or the list of waves inside a given run.

## Example

Considering that test.cou contains one run and test2.cou contains three runs,

```
puts "[load_file test.cou]"
```

Implies "Run0" will be used as the run identifier label.
puts "[load_file test2.cou]"
Implies "Run1 Run2 Run3" will be used as the identifier labels.

```
puts "[disp_file]"
```

Implies "Run0 Run1 Run2 Run3" will be used as the identifier labels.

```
puts "[disp_file Run0]"
```

Implies " $\mathrm{V}(1) \mathrm{I}(\mathrm{R} 1)$ " will be used as the identifier labels.

## UNLOAD_FILE

unload_file all
unload_file \$identifier
Removes all or a single run from memory.

- identifier
a valid run identifier or keyword "all" to remove all runs.


## Miscellaneous Commands

In the following descriptions, the syntax is shown immediately after the function name, then a short description, then, if applicable, descriptions of the arguments.

## DISPLAY

display \$ppl_object
Writes the content of PPL objects to the standard output.

- ppl_object

A reference to a PPL object. Usually, references for waves start with WV and references for numbers start with DB.

## GETSIZE

getsize \$wv_in
Returns the number of points in a wave.

## GETPOINT

getpoint \$wv_in \$ptindex
Returns the x value, real and imaginary parts of a wave point.

- ptindex

Index of a point (between [0; size[).

## SETPOINT

setpoint \$wv_in \$ptindex \$xvalue \$yvalue \$yimgvalue
Modifies a wave point value.

- ptindex

Index of a point (between $[0 ;$ size]).

- xvalue

New x-axis value.

- yvalue

New real part value.

- yimgvalue

New imaginary part value.

## CREATEVECTOR

createVector vectorName \$xlist \$ylist
Creates a vector from a list of ( $\mathrm{x}, \mathrm{y}$ ) values.
You must first load a .cou file prior to using the createVector command. It can be any .cou file.

- vectorName
the name of the PPL object which will represent the vector in the library.
- xlist

A list of ordered $x$ values.

- ylist

A list of values (same length as xlist).

## Example

```
load_file dummy.cou
createVector essai "0 1e-9 2e-9 3e-9 4e-9" "1.1 2.2 3.3 4.4 5.5"
```


## Chapter 23 IBIS Models Support in Eldo

## Introduction

I/O Buffer Information Specification (IBIS) is an ANSI/EIA-656 standard that is developing a specified industry standard method to electronically transport input/output buffers modeling data between semiconductor vendors, EDA tool vendors and end customers.

Eldo supports IBIS version IBISv4.2.
This chapter provides a brief introduction and background to IBIS, lists the current state of IBIS support in Eldo, and provides the syntax and its description for simulating either individual IBIS buffers or entire components. General notes and options related to the IBIS support in Eldo are also described, and some illustrative examples provided. Finally, the chapter ends with some tutorials. It is not intended to provide a detailed description of the IBIS standard in this chapter.

## IBIS Background

IBIS was originally developed by Intel ${ }^{\circledR}$ Corporation in the early 1990s. With the participation of more companies and industry members, IBIS Open Forum was created to promote the IBIS development and to make sure that standard exists. In 1995 the IBIS Open Forum teamed with the EIA. Since then the EIA/IBIS Open Forum oversaw all technical developments of IBIS.

The IBIS committee provides a new version every one or two years. Each version adds more features that the EDA tool vendors should support, and describes how the related input data is formatted. The latest IBIS standard is IBIS version 4.2 which was ratified by the EIA IBIS Open Forum on June 2, 2006 and formally ratified as ANSI/EIA-656-B on September 1, 2006.

IBIS is a behavioral model that describes the electrical characteristics of the I/O buffers using V/I and V/T tables. It has the advantage of not showing any proprietary information. Moreover, the use of behavioral simulation, instead of transistor level simulation, helps in accelerating the signal integrity analysis and the overall design cycle. It is important to note that IBIS does not provide the models themselves but describes how the input data to the EDA tool is formatted. An IBIS file contains data not only about individual buffers but also about an entire component (IC) including pin-to-buffer mapping and package parasitics.

## Using IBIS Models in Eldo

Using IBIS in Eldo is similar to using other SPICE elements, such as transistors. You specify a name for the buffer, the nodes to which the buffer is connected to the rest of the circuit, and
parameters to refer to a model for the buffer and the IBIS file where the model is located. In Eldo you specify the name of the IBIS element with the prefix _IO_.

Eldo can simulate IBIS devices either individually or in the overall component. Eldo supports external models/circuits written in SPICE or Verilog-A. External models/circuits written in VHDL-AMS and Verilog-AMS can be simulated using Questa ADMS. Eldo is compatible with HSPICE syntax, under option compat, except for multilingual model Support.

See "IBIS Support in Eldo" on page 1301 for further information.

## IBIS Resources on the Web

The best way to learn about IBIS is to review the IBIS specification, published papers and sample models. Extensive IBIS information is available on the web as follows:

- Official IBIS Open Forum website
http://www.eigroup.org/ibis/
- Mentor Graphics IBIS Modeling Resources
http://www.mentor.com/products/pcb/expedition/modeling_resources.cfm
Through these web sites you can: receive technical support; review articles, presentations and FAQs; find links to most public IBIS models from semiconductor and connector supplier sources; get free tools and documents that help create an IBIS model; and retrieve the IBIS specifications.


## IBIS File Types and Structures

There are three supported file types within the IBIS modeling framework:

- IBIS files, *.ibs

The IBIS file is the main file that contains the basic information about the component(s) and their internal buffers. The .ibs file also contains information about the package electrical characteristics (package model).

- Package files, *.pkg

Advanced package models can be either placed inside the .ibs file itself or in a package file (.pkg).

- Electrical board description files, *.ebd

An electrical board description file (.ebd file) is defined to describe the connections of a board level component between the board pins and its components on the board.

The IBIS files contain the same basic information and can be thought of as having three main sections:

- Header section - contains information about the IBIS version, the file name, and the process or organization responsible for the information
- Component section-describes the component name, pinout, pin to buffer mapping, and package electrical characteristics
- Model section-describes the behavior of each unique buffer used in a component

An IBIS .ibs file consists of:

- File Header Section
- [Component]
- [Model]
- [Define Package Model]
- [End]

A package .pkg file consists of:

- File Header Section
- [Define Package Model]
- [End]

An electrical board description file .ebd file consists of:

- File Header Section
- [Begin Board Description]
- [End]


## Checking IBIS Files with the Golden Parser

The golden parser is a syntax-checking program that aids the development and verification of IBIS data files. It is available in executable format, compiled for a variety of operating systems, free of charge through the IBIS website (http://www.eigroup.org/ibis/tools.htm).

The latest version of this parser, ibischk4 v4.2.2, is integrated inside Eldo. The golden parser produces warnings and errors which are displayed in the Eldo output by default when an IBIS file is incorporated in the simulation netlist.

## IBIS Device Standards

## Buffers

IBIS is a modeling technique that provides a simple table-based buffer model for semiconductor devices. IBIS models can be used to characterize I/V output curves, rising/falling transition waveforms, and package parasitic information of the device. There are four types of buffer in IBIS:

- Single-ended buffer
- Pseudo-differential buffer
- True differential buffer
- Series buffer

IBIS also defines a global list of port names with fixed functionality that can be applied to all types of buffers. Eldo uses the same port naming and definition for the buffer equivalent subcircuit. Table 23-1 lists the port names and their descriptions. Port names starting with "A" are used to define analog ports while those starting with "D" are used to define digital ports.

Table 23-2 lists all the available buffer types, assigns a number for each type, lists nodes used by buffer type, and provides the $\min / m a x$ number needed for each buffer type. "[ ]" is used to denote optional nodes. Pseudo-differential buffers are recognized as a separate buffer type by the IBIS standard and are constructed from two single-ended buffers. Therefore, pseudodifferential buffer nodes can be obtained from their single-ended version by replacing "a_signal" with "a_signal_pos" and "a_signal_neg". PN is used to denote the power nodes, which are:

- a_pcref - a_gcref for Input, Input_ECL, Terminator, and Input_diff buffers.
- a_pcref - a_gcref - a_puref - a_pdref for other types.

Table 23-1. List of Predefined Port Names and their Descriptions

| Port Name | Description |
| :--- | :--- |
| A_signal | I/O signal port for a model unit |
| A_signal_pos | Non-inverting port of a differential model |
| A_signal_neg | Inverting port of a differential model |
| A_pos | Non-inverting port for series or series switch models |
| A_neg | Inverting port for series or series switch models |
| A_puref | Voltage reference port for pull-up structure |

Table 23-1. List of Predefined Port Names and their Descriptions

| Port Name | Description |
| :--- | :--- |
| A_pcref | Voltage reference port for power clamp structure |
| A_pdref | Voltage reference port for pull-down structure |
| A_gcref | Voltage reference port for ground clamp structure |
| A_gnd | Global reference voltage port |
| D_drive | Digital input to a model unit |
| D_enable | Digital enable for a model unit |
| D_receive | Digital receive port of a model unit, based on data on A_signal <br> (and/or A_signal_pos and A_signal_neg) |
| D_switch | Digital input for control of a series switch model |

Table 23-2. Buffer Types and Port Names Used

| Type | Number | Nodes (in order) | Min/Max |
| :--- | :--- | :--- | :--- |
| Input | 1 | a_signal - [d_receive] - [PN] | $1 / 4$ |
| Output | 2 | a_signal - d_drive - [PN] | $2 / 6$ |
| I/O | 3 | a_signal - d_drive - d_enable - [d_receive] - [PN] | $3 / 8$ |
| 3-state | 4 | a_signal - d_drive - d_enable - [PN] | $3 / 7$ |
| Open_drain | 5 | a_signal - d_drive - [PN] | $2 / 6$ |
| I/O_open_drain | 8 | a_signal - d_drive - d_enable - [d_receive] - [PN] | $3 / 8$ |
| Open_sink | 7 | a_signal - d_drive - [PN] | $2 / 6$ |
| I/O_open_sink | 8 | a_signal - d_drive - d_enable - [d_receive] - [PN] | $3 / 8$ |
| Open_source | 9 | a_signal - d_drive - [PN] | $2 / 6$ |
| I/O_open_source | 10 | a_signal - d_drive - d_enable - [d_receive] - [PN] | $3 / 8$ |
| Input_ECL | 11 | a_signal - [d_receive] - [PN] | $1 / 4$ |
| Output_ECL | 12 | a_signal - d_drive - [PN] | $2 / 6$ |
| I/O_ECL | 13 | a_signal - d_drive - d_enable - [d_receive] - [PN] | $3 / 8$ |
| 3-state_ECL | 14 | a_signal - d_drive - d_enable - [PN] | $3 / 7$ |
| Series | 15 | a_pos - a_neg | 2 |
| Series_switch | 16 | a_pos - a_neg - [d_switch] | $2 / 3$ |
| Terminator | 17 | a_signal - [PN] | $1 / 3$ |
| Input_diff | 18 | a_signal_pos - a_signal_neg - [d_receive] - [PN] | $2 / 5$ |

Table 23-2. Buffer Types and Port Names Used

| Type | Number | Nodes (in order) | Min/Max |
| :--- | :--- | :--- | :--- |
| Output_diff | 19 | a_signal_pos - a_signal_neg - d_drive - [PN] | $3 / 7$ |
| I/O_diff | 20 | a_signal_pos - a_signal_neg - d_drive - d_enable <br> - [d_receive] [PN] | $4 / 9$ |
| 3-state_diff | 21 | a_signal_pos - a_signal_neg - d_drive - d_enable <br> $-[\mathrm{PN}]$ | $4 / 8$ |

## Single-Ended Buffers

## Input and Input_ECL buffers

Figure 23-1 shows the model of an Input buffer (receiver). It has two sets of I-V curves, a ground clamp and a power clamp, and the die capacitance $C_{-} \operatorname{comp}$. Two thresholds are defined, Vinl and Vinh, that determine the buffer's digital output, d_receive.

Figure 23-1. Input Buffer Model Building Blocks


The following relation gives the digital output for the non-inverting buffers:
Vd_receive $=$
1.0 V if Va_signal > Vinh
0.5 V if Vinl < Va_signal < Vinh
0.0 V if Va_signal < Vinh

If Vinl and Vinh are not specified in the IBIS file, the default values of Vinl $=0.8 \mathrm{~V}$ and $\operatorname{Vinh}=2.0 \mathrm{~V}$ are assumed for an Input buffer and Vinl $=-1.475 \mathrm{~V}$ and Vinh $=-1.165 \mathrm{~V}$ are assumed for an Input_ECL buffer.

## Terminator Buffers

A Terminator is an input-only model that can have analog loading effects on the circuit being simulated, but has no digital output. The Terminator model is shown in Figure 23-2. It may contain termination elements like Rgnd, Rpower, Rac, and Cac in addition to the usual clamping diodes circuitry.

Figure 23-2. Terminator Buffer Model Building Blocks


## Output and Output_ECL buffers

Figure 23-3 shows the model of an Output buffer (driver). It has four sets of I-V curves, a ground clamp, a power clamp, a pull-up network and a pull-down network, and the die capacitance $C_{-}$comp. In addition, the transient switching characteristics of the pull-up and pulldown networks are also defined.

Figure 23-3. Output Buffer Model Building Blocks


IBIS provides two ways for defining the switching characteristics:

- If the output switching (V-T) waveform of a buffer can be approximated by a linear ramp then the V-T data may be reported as a rising and falling ramp rate (dV/dt) by using the [Ramp] keyword.
- Using the [Rising Waveform] and [Falling Waveform] keywords if the output switching waveform of the buffer is significantly non-linear.

In both cases the transient current is considered to be a factor from the DC (steady state) current and this factor is calculated from the provided switching data. There are two factors; $k \_p u l l u p$ and $k \_p u l l d o w n$. These factors range from 0 , representing a switched off pull-up/pull-down network, to 1 , representing a fully switched on network. The switching starts when $d \_d r i v e$ crosses 0.5 V and according to the buffer polarity, inverting or non-inverting, the appropriate network is switched on or off.

Output_ECL buffer differs from Output buffer in that the a_pdref is internally connected to the a_puref; that is, pull-up and pull-down share the same power reference. Output and Output_ECL buffers also differ in the conventions related to the [Pulldown], [Temperature Range], [Pin Mapping] keywords and the measuring conditions of the switching characteristics.

## I/O and I/O_ECL Buffers

Figure 23-4 shows the model of an I/O buffer. The $d$ _enable signal determines if the buffer will operate as an Input or Output buffer. If the buffer is active low, then it will behave as an Output buffer if d_enable $<0.5 \mathrm{~V}$ and as an Input buffer otherwise. If the buffer is active high, then it will behave as an Output buffer if $d$ _enable $>0.5 \mathrm{~V}$ and as an Input buffer otherwise.

## Figure 23-4. I/O Buffer Model Building Blocks



When behaving as an Output buffer, I/O_ECL buffer differs mainly from I/O buffer in that the a_pdref is internally connected to the a_puref; that is, pull-up and pull-down share the same power reference. I/O and I/O_ECL buffers also differ in the conventions related to [Pulldown], [Temperature Range], [Pin Mapping] keywords and the measuring conditions of the switching characteristics. Otherwise, if behaving as an Input buffer, I/O and I/O_ECL buffers differ in the default values of Vinl and Vinh (see "Input and Input_ECL buffers" on page 1290 for details).

## 3_state and 3_state_ECL Buffers

The model of a 3_state buffer is show in Figure 23-5. The 3_state buffer is very similar to the I/O buffer but does not have a digital output. It either works as an output buffer when enabled or high impedance when not enabled. The high impedance state is described by the Power Clamp, GND Clamp and die capacitance, C_comp.

Figure 23-5. 3_state Buffer Model Building Blocks


3_state_ECL buffer differs mainly from 3_state buffer in that the a_pdref is internally connected to the a_puref; that is, pull-up and pull-down share the same power reference. 3_state and 3_state_ECL buffers also differ in the conventions related to [Pulldown], [Temperature Range], [Pin Mapping] keywords and the measuring conditions of the switching characteristics.

## Buffers with Open Drain, Sink, or Source

The open drain and open sink are buffers that do not include a pull-up network; that is, the output can sink current only. Earlier IBIS versions used the term "open drain", however, this may be confusing for NMOS and PMOS networks, and so the term "open sink" is now used to describe a buffer that can sink current only. The "open drain" terminology is retained for backward compatibility.

The open source buffer is a buffer that does not include a pull-down network; that is, the output can source current only.

## Pseudo-Differential Buffers

The [Diff Pin] keyword in the IBIS file is used to create a pseudo-differential buffer from two already existing single-ended buffers.

A pseudo-differential input buffer consists of two single-ended input buffers as shown in Figure 23-6. The digital outputs of these two single-ended buffers are tied together and labeled by $d_{\text {_receive. }}$ One single-ended buffer's input is taken to be the non-inverting input (a_signal_pos) while the second one is taken to be the inverting input (a_signal_neg). The
differential input threshold is denoted by Vdiff and is provided under the [Diff Pin] keyword in the IBIS file.

## Figure 23-6. A Pseudo-Differential Input Buffer Consisting of two Single-Ended Input Buffers



The digital output d_receive is given by:
d_receive $=$

- 1 V if a_signal_pos $-a_{-}$signal_neg $>\mathrm{V}_{\mathrm{diff}}$
- 0 V if a_signal_pos - a_signal_neg < $\mathrm{V}_{\mathrm{diff}}$

The pseudo-differential output buffer consists of two single-ended output buffers as shown in Figure 23-7. One single-ended buffer's output is taken to be the non-inverting output (a_signal_pos) while the second one is taken to be the inverting output (a_signal_neg). The differential delay between the two outputs is denoted by tdelay and provided under the [Diff Pin] keyword in the IBIS file.

Figure 23-7. A Pseudo-Differential Output Buffer Consisting of two SingleEnded Output Buffers


The two inputs are tied together and the overall differential buffer has one input and two outputs. Positive differential delay means the non-inverting output is delayed with respect to the inverting output. Inverting differential delay means inverting output is delayed with respect to the non-inverting output.

## True Differential Buffers

The native IBIS does not support true differential buffers, they are only supported using the external model format created using SPICE or Verilog-A.

SPICE or Verilog-A formatted models are pure analog. Eldo is responsible for handling the A/D and D/A conversions as shown in Figure 23-8. Specification of these A/D and D/A blocks are defined in the IBIS file.

Figure 23-8. An Analog-Only Model init using an I/O Buffer as an Example


## Series Buffers

Series and Series_switch buffers can be passive circuits containing various combinations of inductors, resistors and capacitors, as well as the steady state I-V characteristics of non-linear devices such as diodes and transistors. Series and Series_switch are identical in their elements, the only difference is that the latter one can be switched ON or OFF. The IBIS specifications do not define the transition characteristics of a Series_switch. Switches are assumed to either be ON or OFF during a simulation, and I-V characteristics could be defined for either or both states. Switching does not occur during simulation, but you must decide whether the element is ON or OFF before the simulation starts.

The electrical models for the Series / Series_switch are:

- R Series, L Series, R1 Series, C Series, Lc Series and Rc Series These enable IBIS to model simple passive models and/or parasitics. The model is shown in Figure 23-9.

Figure 23-9. Simple Passive Modeling


- Series Current
under which the data points define the I-V tables for voltages measured at Pin 1 with respect to Pin 2. The model is shown in Figure 23-10. Currents are considered positive if they flow into Pin 1.

Figure 23-10. Series Current Modeling


- Series MOSFET
under which the data points define the I-V tables for voltages measured at Pin 2 for a given Vds setting. Currents are considered positive if they flow into Pin 1. The model is shown in Figure 23-11.

Figure 23-11. Series MOSFET Modeling


## Package

IBIS has many ways for package modeling, differing in their complexity and accuracy. The simplest, least accurate, way is to assume all the package pins are identical and uncoupled. The common package parasitics, $R_{-} p k g, L \_p k g$ and $C \_p k g$ shown in Figure 23-12, are defined under the [Package] keyword in the IBIS file. Also unique parasitics $R \_p i n, L \_p i n$ and $C \_p i n$ can be defined separately for each pin under the [Pin] keyword.

Figure 23-12. Each Pin is Assumed to have Parasitic Resistance R_pkg, Inductance L_pkg, and Capacitance C_pkg


More advanced package modeling can be achieved using the [Package Model] keyword, where you can refer to a package model inside the .ibis file or in a .pkg file. You can model the package as coupled pins and give the resistance, inductance and capacitance matrices (RLC matrices) elements of the package pins network. These matrices assume the Maxwellian format.

Another way of modeling is to divide the package into stub sections and define the electrical parameters for each section. The stub represents the physical connection between the package pin and the die pad. Each section is described in terms of its L/R/C per unit length and the Fork and Endfork subparameters allow any path to branch. For example, this can describe the parasitics of the wire bond between the die pad and the package pin. This stub can be treated as lumped or distributed elements depending on whether the section length is 0 or not.

## Component

As mentioned earlier, Eldo can simulate IBIS devices either individually or in the overall component. The component simulation means creating all the buffers inside the component, connecting these buffers to the appropriate nodes and power buses, creating the package parasitics and connecting buffer die pads to the package parasitics. Several keywords and subparameters in the IBIS file are used in a component simulation in addition to that used in the individual buffer simulation:

- [Pin Mapping] is used to define the buffers sharing the same power/ground bus.
- [Series Pin Mapping] is used to join two die pads by a series buffer and [Series Switch Groups] is used to define switching combinations of series switches.
- [Circuit Call] and [Node Declarations] create subcircuits from external circuit models written in SPICE or Verilog-A language, and make their interconnections.
- [Package Model] defines an advanced package model, taking coupling effects into account.


## Pin Mapping

When the input of a buffer(s) changes from High to Low, the output driver current (Ldi/dt) creates a fluctuation between the core ground and power buses. This creates a pulse that can affect static buffer(s) output, causing the receiver(s) to switch inappropriately. A similar effect occurs when the input of a buffer(s) changes from Low to High. The difference between the core ground and power is referred to as "ground bounce." The amount of ground bounce is dependent on the number of outputs changing state at the same time and thus the ground bounce may also be called "simultaneous switching output noise" (SSON).

The [Pin Mapping] keyword, in the IBIS file, contains information on how power supplies are connected to individual buffers or groups of buffers that can be used for predicting SSON. The bus connections (from buffer nodes to supply or ground nodes) described by [Pin Mapping] are assumed as ideal shorts, and do not override parasitic information given for power and/or ground pins. Figure 23-13 indicates how the model is constructed. For example, pins 8 and 12 are connected to the Power bus; pins 10 and 38 are connect to the Ground bus; and the models with signal terminals connected to pins 35 and 40 use these buses for their voltage supplies.

Figure 23-13. [Pin Mapping] Contains Information about Bus Connection from Buffer Nodes to Supply/ Ground Nodes


## Series Pin Mapping and Series Switch Groups

[Series Pin Mapping] allows modeling of elements in series with a signal path, as shown in Figure 23-14. They are particularly useful for modeling elements placed between the terminals
of differential buffers. However, the [Series Pin Mapping] keyword can generally be used to connect series elements between the die pads of any buffers inside the component.

Figure 23-14. Series Elements can be Connected Between Buffer Die Pads using the [Series Pin Mapping] Keyword


IBIS defines two categories of series elements; series and series switch. Series and series switch are identical in their elements. The only difference is that series switch can be switched ON or OFF. Series switches are divided into groups, and the group name to which the series switch belongs to, is defined in the function_table_group column in the IBIS file. The [Series Switch Groups] keyword is used to define switching combinations of series switch groups. You can specify the state of some groups to be ON and it is implicitly assumed that unspecified groups are OFF, or vice versa.

## Node Declarations and Circuit Call

The [External Circuit] keyword allows you to define any block behavioral models, written in SPICE or Verilog-A, with any number of ports and with any functionality. The connectivity of these blocks to each other, to die nodes or die pads, must be defined using the [Node Declaration] and [Circuit Call] keywords. Only one [Node Declarations] keyword is permitted for each [Component] keyword. Multiple [Circuit Call] keywords may appear under a [Component] using the same [External Circuit] name if multiple instantiations of an [External Circuit] are needed.

## Electrical Board Description

A "board level component" is a term describing a printed circuit board (PCB) or substrate which can contain components or even other boards, and which can connect to another board through a set of user visible pins. The electrical connectivity of such a board level component is referred to as an Electrical Board Description (EBD). An EBD file (.ebd) describes the connections of a board level component between the board pins and its components on the
board. An .ebd file is intended to be a stand-alone file, not referenced by or included in any .ibs or .pkg files.

The IBIS EBD describes the connection between the user accessible pins of a board level component and other pins of the board or pins of the ICs mounted on that board. Each pin-tonode connection is divided into one or more cascaded sections, where each section is described in terms of its L/R/C per unit length. The Fork and Endfork subparameters allow any path to branch to multiple nodes, or another pin. A path description is required for each pin whose signal name is not GND, POWER or NC.

## IBIS Support in Eldo

Eldo supports IBIS version IBISv4.2, this is the default. Releases prior to AMS 2007.2 supported IBISv2.1. The v4.2 support is a new implementation, not an extension to v2.1. You can select the old v2.1 solution, instead of the v4.2 one, using the Eldo option and IBIS instance keyword, IEVER=1.

Eldo can simulate IBIS devices either individually or in the overall component. See "Supported Keywords and Sub-Parameters" on page 1324 for further information.

## Analysis Types

IBIS specifications provide data about the large signal behavior of the I/O buffers and their switching characteristics. However, no data about the frequency domain behavior is provided. Therefore, IBIS simulation can be performed in either the DC or Transient domain. IBIS simulation is supported in Eldo using:

- DC analysis
- Transient analysis


## Digital Levels

IBIS defines both analog and digital ports. Table 23-3 and Table 23-4 show the different digital ports logic levels and the corresponding analog levels.

Table 23-3. Digital Port Logic Levels

| Analog Input | Digital Input: d_drive, d_enable and d_switch |
| :--- | :--- |
| Vin $>0.5 \mathrm{~V}$ | Logic "1" |
| Vin $<0.5 \mathrm{~V}$ | Logic "0" |

Table 23-4. Analog Levels

| Digital Output: d_receive | Analog Output |
| :--- | :--- |
| Logic "1" | 1.0 V |
| Logic "0" | 0.0 V |
| Logic "X" | 0.5 V |

## IBIS Buffers

## Syntax

You can reference an IBIS buffer by a model name, or a pin of component. The syntax of IBIS buffers is as follows:

## Single-Ended Buffer

```
_IO_xx ASG [DDR] [DEN] [DRX] [PCR GCR PUR PDR] file="path"
+ model="model_name"|pin="pin_name" [component="component_name"]
+ [device=type_name|type_number] [corner=TYP|MIN|MAX|FAST|SLOW]
+ [warn=ON|OFF] [nowarn] [power=ON|OFF]
+ [c_comp_pu=value] [c_comp_pd=value]
+ [c_comp_pc=value] [c_comp_gc=value]
+ [use_fall_wvf=0|1|2] [use_rise_wvf=0|1|2]
+ [k_pulldown=node] [k_pullup=node]
+ [model_selector='msel_1=mdl_1 [,..., msel_n=mdl_n]'] [msel_mode=value]
+ [package=0|1 | 2|3|OFF|CMPNT|PIN|PKGMOD] [pkg_model="pkg_model_name"]
+ [rx_logic=0|1]
+ [para_begin param1=value1 param2=value2 ... para_end]
+ [eldova=ON|OFF] [em_libname="logical_lib_name"]
+ [table_tune=value]
+ [logic_one=value] [logic_zero=value]
+ [c_fixture=YES|NO|IGNORE]
```


## Pseudo-Differential Buffer

```
_IO_xx ASP ASN [DDR] [DEN] [DRX] [PCR GCR PUR PDR] file="path"
+ component="component_name" pin="pin_name" inv_pin="inv_pin_name"
+ [corner=TYP |MIN|MAX|FAST|SLOW] [warn=ON|OFF] [nowarn] [power=ON|OFF]
+ [c_comp_pu=value] [c_comp_pd=value]
+ [c_comp_pc=value] [c_comp_gc=value]
+ [use_fall_wvf=0|||2] [use_rise_wvf=0|1| 2]
+ [model_selector='msel_1=mdl_1 [,..., msel_n=mdl_n]'] [msel_mode=value]
+ [package=0|1 | 2|3|OFF|CMPNT|PIN|PKGMOD] [pkg_model="pkg_model_name"]
+ [para_begin param1=value1 param2=value2 ... para_end]
+ [eldova=ON|OFF] [em_libname="logical_lib_name"]
+ [table_tune=value]
+ [logic_one=value] [logic_zero=value]
+ [add_series_terminator=YES|NO|IFA]
+ [c_fixture=YES|NO|IGNORE]
```


## True Differential Buffer

```
_IO_xx ASP ASN [DDR] [DEN] [DRX] [PCR GCR PUR PDR] file="path"
+ model="model_name"|pin="pin_name" [inv_pin="inv_pin_name"]
+ [component="component_name"]
+ [device=type_name|type_number] [corner=TYP|MIN|MAX|FAST|SLOW]
+ [warn=ON|OFF] [nowarn] [power=ON|OFF]
+ [model_selector='msel_1=mdl_1 [,.., msel_n=mdl_n]'] [msel_mode=value]
+ [package=0|1|2|3|OFF|CMPNT|PIN|PKGMOD] [pkg_model="pkg_model_name"]
+ [para_begin param1=value1 param2=value2 ... para_end]
+ [eldova=ON|OFF] [em_libname="logical_lib_name"]
+ [table_tune=value]
+ [add_series_terminator=YES|NO|IFA]
```


## Series Buffer

```
_IO_xx APV ANV [DST] file="path"
+ model="model_name"
+ [device=type_name|type_number][corner=TYP|MIN|MAX|FAST|SLOW]
+ [warn=ON|OFF] [nowarn]
+ [ss_state=ON|OFF] [all_sm=YES|NO]
+ [keep_vds_monotonic=NO|YES] [keep_vgs_monotonic=NO|YES]
+ [model_selector='msel_1=mdl_1 [,.., msel_n=mdl_n]'] [msel_mode=value]
+ [para_begin param1=value1 param2=value2 ... para_end]
+ [eldova=ON|OFF] [em_libname="logical_lib_name"]
```


## Parameters

Some parameters are part of the IBIS standard, please refer to description in "IBIS Device Standards" on page 1288.

- _IO_xx

IBIS instance name.

- ASG

Name of the a_signal node.

- ASP

Name of the a_signal_pos node.

- ASN

Name of the a_signal_neg node.

- DDR

Name of the d_drive node.

- DEN

Name of the d_enable node.

- DRX

Name of the d_receive node.

- APC

Name of the a_pcref node.

- AGC

Name of the a_gcref node.

- APU

Name of the a_puref node.

- APD

Name of the a_pdref node.

- APV

Name of the a_pos node.

- ANG

Name of the a_neg node.

- DST

Name of d_switch node, this node is used only for Series_Switch buffers that reference an external model.

## Note

Buffer external nodes should be listed in order, depending on the type of the buffer model. A list of the buffer model types and corresponding ports are in Table 23-2 on page 1289.

- file="path"

Specifies the path to the file that contains an IBIS formatted model.
This can be the full path (for example, /user/test/Models/model.ibs), a relative path, or just a file name. Both / and $\backslash$ are acceptable as separators in the path name for the UNIX and Windows platforms. An Eldo option IBIS_SEARCH_PATH is available to specify the path to the directory to search for the IBIS files.

- model="model_name"

Specifies an IBIS model name within the specified IBIS file, it can be either a model name or a model selector name. Model name is case-sensitive.

- pin="pin_name"

Specifies a pin name within the specified component.
Note
The keywords pin and model are exclusive. It is an error to specify both these keywords in the same _IO_card.

- inv_pin="inverting_pin_name"

Specifies a pin name within the specified component; this is to be used with the pseudo/true differential buffers. Pin name and inverting pin name must match a differential pins pair under [Diff Pin] IBIS keyword.

- component="component_name"

Specifies a component name within the specified IBIS file. The component name is casesensitive. Component name must be specified if pin name or inverting pin name is specified, while it is optional if you specify a model name.

- device="type_name|type_number"

Specifies the desired buffer type to be used; this is to check the buffer type assignment in the IBIS instance against the buffer type given in the IBIS file. A list with buffer types and numbers are given in Table 23-2 on page 1289.

- corner=TYP|MIN|MAX|FAST|SLOW

Specifies the IBIS corner to be used to extract the data from the IBIS file. The default is corner=TYP-if any data is missing under the Min or Max columns in the IBIS file then the Typ column value will be used instead. When corner=TYP, MIN, or MAX, simulation will extract the data under the corresponding Typ, Min, and Max columns in the IBIS file. When corner=FAST or SLOW, corner uses combinations from data under the Min and Max columns; FAST is the same as MAX, and SLOW is the same as MIN except for parameters listed in Table 23-5.

Table 23-5. Exceptions to Fast=Max, Slow=Min Rule

| Parameter/Data | Fast | Slow |
| :--- | :--- | :--- |
| C_comp | Min | Max |
| [Cac] | Min | Max |
| [Gnd Clamp Reference] | Min | Max |
| [Pulldown Reference] | Min | Max |
| [Package] | Min | Max |

## - power=ON|OFF

When power=ON (the default), the reference voltage sources are connected to the buffer reference ports $a \_p c r e f, a \_g c r e f, a \_p u r e f, a \_p d r e f$ internally. When power=OFF you are responsible for connecting the voltage sources externally, if you set power=OFF but do not specify the power nodes in the _IO_ card, then OFF will be ignored and internal references will be created.

Power nodes can be specified when power=ON to allow you to print/plot the values of voltage sources connected to these nodes internally, in this case you must not connect external voltage sources to these nodes.

- warn=ON|OFF

Specifies if the warning message generated for this instance should be printed: ON, or suppressed: OFF. Setting warn=OFF is equivalent to using the keyword nowarn. The default setting is ON.

- nowarn

This is equivalent to warn=OFF.

- c_comp_pu=value, c_comp_pd=value, c_comp_pc=value, c_comp_gc=value

These four keywords are optional. If one of these keywords is specified with a non-zero value; the $c_{-}$comp capacitor will be split up to four parts. Values are dimensionless numbers between 0 and 1 , and the sum of them should be equal to 1 . The default is zero for the unspecified values.

- use_fall_wvf= $0|1| 2$, use_rise_wvf= $0|1| 2$

0
Use the ramp for the falling/rising transitions.
1
Use one waveforms for the falling/rising transitions.
2
Use two waveforms for the falling/rising transitions.
The default behavior is to use the first two waveforms if more than one waveform is specified in the IBIS model, use one waveform if only one is specified, and to use ramp if no waveforms are specified.

- k_pulldown="node", k_pullup="node"

The purpose of these keywords is to display the values of the pull-up and pull-down coefficients of the device as a function of time as the device goes through rising or falling transitions.

- msel_mode=value

The value indicates a model order under the [Model Selector] keyword in the IBIS file. If the value given is greater than the model selector list, then the first model will be selected. The default is 1 .

- model_selector='mod_sel1=mod_name1 [, mod_sel2=mod_name2,...]'

Used to select models for some or all model selectors in the given IBIS file. model_selector has a higher precedence over msel_mode.

- package $=0|1| 2|3| \mathrm{OFF}|\mathrm{CMPNT}| \mathrm{PIN} \mid$ PKGMOD

Specifies the package modeling type to be used for package parasitics.
0 or OFF
No package is added.

1 or CMPNT
RLC components defined under [Package] keyword are added, this is the default when specifying model name.

2 or PIN
RLC components defined under [Pin] are added, this is the default when specifying pin name.
3 or PKGMOD
A package model will be used. This is the default.

## Note

If no data is available for selected packaging type, then the data in the lower type will be used.

- ss_state=ON|OFF

For Series Switch buffers, if ss_state=ON, then Eldo will use the data under the [On] keyword: setting it to OFF, the data under [Off] keyword will be used. The default is ON.

- all_sm=YES|NO

For Series/Series_Switch buffers; setting all_sm to NO makes Eldo use only the first non-zero Vds table to generate the current of Series MOSFET elements in the Series buffer. The default is YES.

- keep_vds_monotonic=NO|YES

For Series/Series_Switch buffers; setting keep_vds_monotonic to YES will keep the Ids current monotonic versus Vds values for a given Vgs. Default is NO.

- keep_vgs_monotonic=NO|YES

For Series/Series_Switch buffers; setting keep_vgs_monotonic to YES will keep the Ids current monotonic versus Vgs values for a given Vds. Default is NO.

- rx_logic=0|1

For Input or IO buffers; if the input voltage on a_signal port is between Vinl and Vinh thresholds then rx_logic will control the output voltage on the d_receive port. When $\mathbf{r x}$ logic $=0$ (default), the voltage on the d_receive port will be 0.5 V (representing logic " X "). When rx_logic=1, the voltage on the d_receive port will have the same value (state) as the previous time step.

## Note

If there are hysterises thresholds (Vinl+, Vinl-, Vinh+, and Vinh-) under the [Model Spec] keyword, then rx_logic has no effect.

- para_begin param1=value1 param2=value2 ... para_end

For IBIS buffers that reference an external model, the parameter names and values specified between keywords para_begin/para_end will be passed to the external model module.

- eldova=ON|OFF

For IBIS models that reference an external model in Verilog-A, Eldo will use its Verilog-A compiler to handle these models if eldova=ON. Setting eldova=OFF enables these models to be simulated with Questa ADMS. The default is ON.

- em_libname="logical_lib_name"

For IBIS models that reference external models written in any AMS language, this keyword is optionally used. If no library is specified, the default work library will be used, specified with the vasetlib command or the -lib option of the vasim command. Otherwise, the specified logical_lib_name library is used.

- table_tune=value

Controls Eldo time step when the IBIS buffer is switching to obtain accurate output waveforms. Table_tune accepts non-negative values. Default value is 8 .

Setting a value of 1 forces Eldo to take into account all the switching waveform points, 2 to take one point into account and skip the next, 3 skips two points, but takes into account the third, and so on. Setting a value of 0 makes Eldo control the time step regardless of the switching waveform.

## Note

The actual time step will be the minimum among the time step of the current IBIS buffer, time steps of other IBIS buffers, and the time step forced by Eldo. HMIN is always set as the lower limit for the time step.

- logic_one=value|logic_zero=value

Define the voltage level accepted by IBIS buffers for digital ports, logic_one default is 1.0, and logic_zero default is 0.0. logic_one must be greater than logic_zero by at least 200 mV .

The input voltage is considered 'logic 1 ' if it is greater than (logic_one + logic_zero)/2, and considered 'logic 0 ' if it is below this value.

## Note

These levels are defined for native IBIS buffers and do not apply to external models.

- add_series_terminator=YES|NO|IFA

Used with the pseudo/true differential buffers to enable/disable creation of series models across the differential buffers die pads. Default is NO. IFA is the same as YES but does not produce warning messages if there is no series models defined under [Series Pin Mapping] for the differential buffers pins.

- c_fixture=YES|NO|IGNORE

Enable/disable using rising or falling waveforms that have a c_fixture sub-parameter with a non-zero value. Setting to NO (default) makes Eldo discard these waveforms; YES to use
these waveforms; and IGNORE to use these waveforms but with setting c_fixture value to zero (ignore c_fixture).

## Example

```
IBIS File Example
[IBIS Ver] 3.2
[Comment Char] |_char
[File Name] dummy.ibs
|
```



```
[Component] Test_Component
[Manufacturer] None
[Package]
\begin{tabular}{llll} 
& \multicolumn{1}{c}{ typ } & \multicolumn{1}{l}{ min } & \multicolumn{1}{c}{\(\max\)} \\
R_pkg & 0.020 & 0.017 & 0.025 \\
L_pkg & 0.998 nH & 0.881 nH & 1.069 nH \\
C_pkg & 0.146 pF & 0.118 pF & 0.205 pF
\end{tabular}
\begin{tabular}{llllll} 
[Pin] & signal_name & model_name & R_pin & L_pin & C_pin \\
1 & & & & & \\
2 & NC & NC & 0.019 & \(1.069 n\) & 0.162 p \\
3 & in & MS_In & 0.018 & 0.881 n & 0.121 p \\
4 & out & MS_Out & 0.017 & 1.031 n & 0.205 p \\
& MS_Out & 0.017 & 1.031 n & 0.205 p
\end{tabular}
[Model Selector] MS_In
Input_33 Vcc = 3.3 V
Input_50 Vcc = 5.0 V
|
MModel Selector] MS_Out
Output_33 Vcc = 3.3 V
Output_50 Vcc = 5.0 V
|
[Diff Pin] inv_pin vdiff tdelay_typ tdelay_min tdelay_max
3 4 150mV -1ns 0ns -2ns
[Series Pin Mapping] pin_2 model_name
3 4 Series1
***********************************************************
Model Input_33
[Model] Input_33
Model_type Input
Vinl = 0.99
Vinh = 2.31
|
```



```
|
Model Series1
[Model] Series1
Model_type Series1
variable R(typ) R(min) R(max)
[R Series] 8ohm 6ohm 12ohm
variable L(typ) L(min) L(max)
[L Series] 5nH NA NA
| variable R(typ) R(min) R(max)
[Rl Series] 4ohm NA NA
|
|
[End]
```

The preceding IBIS file example is referenced in the following netlist examples.

- Netlist 1

```
_IO_input1_bymodel IN D_OUT1
+ file="dummy.ibs" model="Input_33"
+ device=input ! or device=1
```

The above netlist calls the buffer by its model name. It instantiates an input buffer input1_bymodel and connects its analog input to node IN and its digital output to node D_OUT1. The buffer description is in the IBIS file dummy.ibs located in the same directory as the netlist. The buffer model, named Input_33, is picked up from the IBIS file.

Note that the component name is not specified; therefore Eldo will not add any package parasitics to the buffer analog input pin. The corner is not specified, therefore the typical data will be used for this buffer by default. The power keyword is not specified, therefore Eldo connects the reference voltage sources to the buffer reference ports.

- Netlist 2

```
_IO_input1_bypin IN D_OUT2 PC GC
+ file="dummy.ibs"
+ component="Test_Component" pin="2"
+ model_selector='MS_In=Input_50' ! equal to msel_mode=2
```

The above netlist calls the buffer by its pin name. It instantiates an input buffer input1_bypin and connects its analog input to node IN and its digital output to node D_OUT2. The buffer description is in the IBIS file dummy.ibs located in the same directory as the netlist. It belongs to the component Test_Component. The buffer model, named

MS_In (the one associated with pin 2), is picked up from the IBIS file. The MS_In model has a model selector statement in the IBIS file. The netlist selects the Input_50 model for MS_In.

The package keyword takes the default of 2 because the buffer is instantiated by pin name. Therefore Eldo will add the package parasitics associated with pin 2 under the [Pin] keyword, $\mathrm{R}=0.018 \mathrm{~L}=0.881 \mathrm{n} \mathrm{C}=0.121 \mathrm{p}$, to the buffer analog input pin. The corner is not specified, therefore the typical data will be used for this buffer by default. The power keyword is not specified, therefore Eldo connects the reference voltage sources to the buffer reference ports. In this case the nodes PC and GC only have the role of enabling you to plot/print the voltage reference values.

- Netlist 3

```
* make pseudo-differential buffer for pin 3 and pin 4
_IO_out_diff OUTp OUTn d_CTRL
+ file="dummy.ibs" component="Test_Component"
+ pin="3" inv_pin="4"
```

The above netlist instantiates the pseudo-differential buffer associated with pins 3 and 4 . The non-inverting pin of the buffer is connected to node OUTp, inverting pin to node OUTn, and the digital input to node d_CTRL. The buffer description is in the IBIS file dummy.ibs located in the same directory as the netlist. It belongs to the component Test_Component.

The package keyword takes the default of 2 because the buffer is instantiated by pin name. Therefore Eldo will add the package parasitics associated with pin 3 and 4 under the [Pin] keyword, $\mathrm{R}=0.017 \mathrm{~L}=1.031 \mathrm{n} \mathrm{C}=0.205 \mathrm{p}$, to the buffer analog input pins. The corner is not specified, therefore the typical data will be used for this buffer by default. The power keyword is not specified, therefore Eldo connects the reference voltage sources to the buffer reference ports.

- Netlist 4

```
*connect series buffer between 3 and 4
_IO_ser OUTp OUTn
+ file="dummy.ibs" model="Series1"
```

The above netlist instantiates the series buffer associated with pins 3 and 4. It is connected to nodes OUTp and OUTn. The buffer description is in the IBIS file dummy.ibs located in the same directory of the netlist. The buffer model is Series1. The corner is not specified, therefore the typical data will be used for this buffer by default.
Note that any series buffer has no package associated with it.

## IBIS Component

```
Syntax
_IO_xx file="path" component="component_name"
+ [corner=TYP|MIN|MAX|FAST|SLOW] [warn=ON|OFF] [nowarn]
+ [model_selector='msel_1=mdl_1 [,..., msel_n=mdl_n]'] [msel_mode=value]
+ [package=0| 1 | 2| 3| 4|OFF| CMPNT |PIN|PKGMOD|MIX]
+ [pkg_model="pkg_model_name"]
+ [ss_group='ON|OFF G1 [,..., Gn]'] [nopseudo]
+ [use_fall_wvf=0|1|2] [use_rise_wvf=0|1|2]
+ [c_comp_pu=value] [c_comp_pd=value] [c_comp_pc=value]
+ [c_comp_gc=value] [all_sm=YES|NO]
+ [keep_vds_monotonic=NO|YES] [keep_vgs_monotonic=NO|YES]
+ [rx_logic=0|1]
+ [eldova=ON|OFF] [em_libname="logical_lib_name"]
+ [table_tune=value]
+ [logic_one=value] [logic_zero=value]
+ [c_fixture=YES|NO|IGNORE]
```


## Parameters

Some parameters are part of the IBIS standard, please refer to description in "IBIS Device Standards" on page 1288.

- _IO_xx

IBIS instance name.

- file="path"

Specifies the path to the file that contains an IBIS formatted model.
This can be the full path (for example, /user/test/Models/model.ibs), a relative path, or just a file name. Both / and $\backslash$ should be acceptable as separators in the path name (for the UNIX and NT versions). An Eldo option IBIS_SEARCH_PATH is available to specify the path to the directory to search for the IBIS files.

- component="component_name"

Specifies a component name within the specified IBIS file. The component name is casesensitive.

- corner=TYP|MIN|MAX|FAST|SLOW

Specifies the IBIS corner to be used to extract the data from the IBIS file. The default is corner=TYP-if any data is missing under the Min or Max columns in the IBIS file then the Typ column value will be used instead. When corner=TYP, MIN, or MAX, simulation will extract the data under the corresponding Typ, Min, and Max columns in the IBIS file. When corner=FAST or SLOW, corner uses combinations from data under the Min and Max columns; FAST is the same as MAX, and SLOW is the same as MIN except for parameters listed in Table 23-5 on page 1305.

- warn=ON|OFF

Specifies if the warning message generated for this instance should be printed (ON), or suppressed (OFF). Setting warn=OFF is equivalent to using the keyword nowarn. The default setting is ON.

- nowarn

This is equivalent to warn=OFF.

- msel_mode=value

The value indicates a model order under the [Model Selector] keyword in the IBIS file. If the value specified is greater than the model selector list, then the first model will be selected. The default is 1 .

- model_selector='mod_sel1=mod_name1 [, mod_sel2=mod_name2 ,...]'

This keyword can be repeated more than once. model_selector is used to select models for some or all model selectors in the given IBIS file. model_selector has a higher precedence over msel_mode.

- package=0|1|2|3|4|OFF|CMPNT|PIN|PKGMOD|MIX

This keyword specifies the package modeling type to be used for package parasitics.
0 or OFF
No package is added.
1 or CMPNT
RLC components defined under [Package] keyword are added.
2 or PIN
RLC components defined under [Pin] are added.
3 or PKGMOD
A package model will be used. This is the default.
4 or MIX
A package model will be used, and RLC parasitics are added as defined under [Pin] section for pins that are not defined in the package model.

## Note

If no data is available for selected packaging type, then the data in the lower type will be used.

- pkg_model="package_model_name"

Specifies an IBIS package model name within the specified IBIS file. The package model name must match one defined for this component under [Package Model] or [Alternate Package Models] keywords. If pkg_model is not specified, the one under [Package Model] will be used. "package_model_name" is case-sensitive.

- ss_group='ON|OFF G1 [,G2, ...]'

Sets the On/Off state for the series switch buffers created according the info under [Series Pin Mapping] keyword.

You can set the logical state of this set of groups by type ON|OFF in the begining of the set, and then follow it by the groups' names that will take this state. The specified set of groups must match one of these under [Series Switch Groups] keyword or its complementary. If ss_group is not specified Eldo will take the first set of groups under [Series Switch Groups] keyword to set the logical state for the series switch buffers.

- nopseudo

When specified Eldo does not generate pseudo-differential buffers for the pseudodifferential pins, and generates single-ended buffers instead.

By default Eldo generates pseudo or true differential buffers as defined under [Diff Pin] keyword.

## Note

The following keywords are used in the generated buffers if applicable.

- c_comp_pu=value, c_comp_pd=value, c_comp_pc=value, c_comp_gc=value

These four keywords are optional. If one of these keywords is specified with a non-zero value; $c_{-}$comp capacitor will be split up to four parts. Values are dimensionless numbers between 0 and 1 , and sum of them should be equal to 1 . The default is 0 for the unspecified values.

- use_fall_wvf= $0|1| 2$, use_rise_wvf= $0|1| 2$

0
Use the ramp for the falling/rising transitions.
1
Use one waveforms for the falling/rising transitions.
2
Use two waveforms for the falling/rising transitions.
The default behavior is to use the first two waveforms if more than one waveform is specified in the IBIS model, use one waveform if only one is specified, and to use ramp if no waveforms are specified.

- all_sm=YES|NO

For Series/Series_Switch buffers. Setting all_sm to NO makes Eldo use only the first non-zero Vds table to generate the current of Series MOSFET elements in the Series buffer. The default is YES.

- keep_vds_monotonic=NO|YES

For Series/Series_Switch buffers. Setting keep_vds_monotonic to YES will keep the Ids current monotonic versus Vds values for a given Vgs. Default is NO.

- keep_vgs_monotonic=NO|YES

For Series/Series_Switch buffers. Setting keep_vgs_monotonic to YES will keep the Ids current monotonic versus Vgs values for a given Vds. Default is NO.

- rx_logic=0|1

For Input or IO buffers; if the input voltage on a_signal port is between Vinl and Vinh thresholds then rx_logic will control the output voltage on the d_receive port. When rx_logic $=0$ (default), the voltage on the d_receive port will be 0.5 V (representing logic " X "). When rx_logic=1, the voltage on the d_receive port will have the same value (state) as the previous time step.

## Note

If there are hysterises thresholds (Vinl+, Vinl-, Vinh+, and Vinh-) under the [Model Spec] keyword, then rx_logic has no effect.

- eldova=ON|OFF

For external models and external circuits written in Verilog-A. Eldo will use its Verilog-A compiler to handle these models if eldova=ON. Setting eldova=OFF enables these models to be simulated with Questa ADMS. The default is ON.

- em_libname="logical_lib_name"

Can be used for external models and external circuits written in any AMS language. The specified logical_lib_name library is used as the work library. If no library is specified, the default work library will be used, specified with the ADMS vasetlib command or the vasim -lib command.

- table_tune=value

Controls Eldo time step when the IBIS buffer is switching to obtain accurate output waveforms. Table_tune accepts non-negative values. Default value is 8 .

Setting a value of 1 forces Eldo to take into account all the switching waveform points, 2 to take one point into account and skip the next, 3 skips two points, but takes into account the third, and so on. Setting a value of 0 makes Eldo control the time step regardless of the switching waveform.

## Note

The actual time step will be the minimum among the time step of the current IBIS buffer, time steps of other IBIS buffers, and the time step forced by Eldo.
HMIN is always set as the lower limit for the time step.

- logic_one=value|logic_zero=value

Define the voltage level accepted by IBIS buffers for digital ports, logic_one default is 1.0, and logic_zero default is 0.0. logic_one must be greater than logic_zero by at least 200 mV .

The input voltage is considered 'logic 1 ' if it is greater than (logic_one + logic_zero)/2, and considered 'logic 0 ' if it is below this value.

Note
These levels are defined for native IBIS buffers and do not apply to external models.

## - c_fixture=YES|NO|IGNORE

Enable/disable using rising or falling waveforms that have a c_fixture sub-parameter with a non-zero value. Setting to NO (default) makes Eldo discard these waveforms; YES to use these waveforms; and IGNORE to use these waveforms but with setting c_fixture value to zero (ignore c_fixture).

## Equivalent subcircuit

Eldo uses the data under the [Component] keyword to generate buffers, interconnections, package parasitics, and SPICE subcircuits or Verilog-A modules that represent external circuit calls. Each component pin that references a model name or model selector name will be associated with a buffer. The pins that are used as differential pairs under the [Diff Pin] keyword will be connected to differential buffers, the other pins will be connected to singleended buffers.

Series/Series_Switch models will be created according to the data under the [Series Pin Mapping] keyword. Power interconnections are done according to the data under the [Pin Mapping] keyword if available; otherwise internal source references are created for each buffer. Package parasitics are added according to the package modeling type specified by the package keyword, and the data available about the package model.

## External nodes naming rules

Component pins that reference anything other than "NC" reserved keywords as the model name will be added to the Eldo netlist as external nodes for the component equivalent subcircuit. If the pin references an "NC" reserved keyword, but is used by the package model or exists in the pin mapping of the series buffers, it will be added to the netlist also.

Additional nodes are also added to make access for buffers input, output, and control signals. These additional nodes should be connected to ground if they will not be used.

The naming rules for the buffers and external nodes are:

- Component pins:
<instance_name>_<pin_name>
- Control nodes:

```
<instance_name>_<buffer_name>_<reserved_node_name>
```

Buffer names are as follows:

- Single-Ended Buffer:

```
<pin_name>
```

- Differential Buffer:

```
<diff_pin_name>_<inv_pin_name>_diff
```

- Series Buffer:

```
<pos_pin>_<neg_pin>_<model_name>_<function__group_name>_sers
```


## Example

This example uses the same IBIS file as that used in the "IBIS File Example" on page 1309.

- Netlist

```
_IO_comp1 file="dummy.ibs"
+ component="Test_component"
.connect _IO_comp1_2_d_receive _IO_comp1_3_4_diff_d_drive
```

The above netlist instantiates the entire component Test_component located in the IBIS file dummy.ibs. The component instance is given the name _IO_comp1. It is composed of an input buffer, a pseudo-differential buffer, and a series buffer (as shown in Figure 23-15). The digital output of the input buffer _IO_comp1_2_d_receive and the digital input of the differential output buffer _IO_comp1_3_4_diff_d_drive are connected in the netlist using the .connect statement.

Figure 23-15. Test_component Example


Figure 23-15 shows the Test_component of the dummy.ibs IBIS file in the "IBIS File Example" on page 1309. The component is instantiated with the name _IO_comp1. The digital output of the input buffer and the digital input of the output buffer are connected in the netlist by the user.

## IBIS Package

## Syntax

_IO_xx file="path" pkg_model="package_model_name"

## Parameters

- _IO_xx

IBIS instance name.

- file="path"

Specifies the path to the file that contains an IBIS formatted model.
This can be the full path (for example, /user/test/Models/model.ibs), a relative path, or just a file name. Both / and $\backslash$ should be acceptable as separators in the path name (for the UNIX and NT versions). An Eldo option IBIS_SEARCH_PATH is available to specify the path to the directory to search for the IBIS files.

- pkg_model="package_model_name"

Specifies an IBIS package model name within the specified IBIS file. package_model_name is case-sensitive.

## Equivalent subcircuit

For each IBIS instance that represents an IBIS package model, Eldo will create an equivalent subcircuit that contains sets of loss-less/lossy transmission lines and/or discrete RLC components.

## Naming rules

External nodes of the equivalent subcircuit will be generated automatically by Eldo. Each pin in the package model will be represented by two external nodes; one at the die-pad side and the other one at the package-pin side. The naming of these pins follows the rules below:

- Node at die side:
<IBIS_instance_name>_<pin_name>_DIEPAD
- Node at package side:
<IBIS_instance_name>_<pin_name>

```
Examples
Package File Example
[IBIS Ver] 4.0
[File Name] package_model_4pins.pkg
[File Rev] 1.0
[Define Package Model] pm1
[Manufacturer] ST None
```

```
[OEM] Unknown
[Description] None
[Number Of pins] 4
[pin Numbers]
pin1
pin2
pin3
pin4
[Model Data]
[Inductance Matrix] Sparse_matrix
|
[Row] pin1
pin1 418n
pin2 125n
|
[Row] pin2
pin2 418n
pin3 125n
|
[Row] pin3
pin3 418n
|
[Row] pin4
pin4 418n
|
[Capacitance Matrix] Sparse_matrix
```



```
[Row] pin1
pin1 94p
pin2 -22p
[Row] pin2
pin2 94p
pin3 -22p
|
[Row] pin3
pin3 94p
|
[Row] pin4
pin4 94p
|
[Resistance Matrix] Sparse_matrix
```



```
[Row] pin1
pin1 15
|
[Row] pin2
pin2 15
|
[Row] pin3
pin3 15
|
[Row] pin4
pin4 15
|
[End Model Data]
[End Package Model]
```

[End]
The preceding package file example is referenced in the following netlist example.

- Netlist

```
_IO_pkg1
+ file=" package_model_4pins.pkg "
+ pkg_model=" pm1"
```

The above netlist instantiates the IBIS package located in the package_model_4pins.pkg IBIS file. The package model name is pm1. It is a four-pin package as shown in
Figure 23-16. This package is described, in the package file, using the RLC matrix representation that accounts for the coupling between the pins. You can access the nodes that reside either inside or outside the package as shown.

Figure 23-16. Package model example


Figure 23-16 shows the package of the package_model_4pins.pkg IBIS file given in the "Package File Example" on page 1319. The package is instantiated with the name _IO_pkg1.

## Electrical Board Description

## Syntax

_IO_xx file="path" ebd_model="ebd_model_name"

+ [ref_des_map='ref_des_1=instance_1 [,..., ref_des_n=instance_n]']


## Parameters

- _IO_xx

IBIS instance name.

- file="path"

Specifies the path to the file that contains an IBIS formatted model.

This can be the full path (for example, /user/test/Models/model.ibs), a relative path, or just a file name. Both / and $\backslash$ should be acceptable as separators in the path name (for the UNIX and NT versions). An Eldo option IBIS_SEARCH_PATH is available to specify the path to the directory to search for the IBIS files.

- ebd_model="ebd_model_name"

Specifies an IBIS Electrical Board Description (EBD) model name within the specified IBIS file. ebd_model_name is case-sensitive.

- ref_des_map='ref_des_1=instance_1 [,..., ref_des_n=instance_n]'

Maps an IBIS buffer component to a reference designator, where:

- instance_n is the name of the Eldo IBIS instance used to describe an IBIS component.
- ref_des_n is the reference designator visible in the Node sub-parameter of the [Path Description] keyword in the EBD file.

Note
Reference designator name and instance name are case insensitive.
ref_des_map can be repeated more than once in the _IO_ card.
If a reference designator is repeated in the ref_des_map, then the instance assigned to that reference designator will be that of the last one.

## Equivalent subcircuit

For each IBIS instance that represents an IBIS EBD model, Eldo will create an equivalent subcircuit that contains sets of loss-less/lossy transmission lines and/or discrete RLC components.

## Naming rules

External nodes of the equivalent subcircuit will be generated automatically by Eldo. Each pin in the EBD model, and each component pin, will be connected to the node in the netlist. The naming of these pins follows the rules below:

- Board pins:
<IBIS_instance_name>_<pin_name>
- Component nodes:
<mapped_ref_des>_<node_name>


## Note

If a reference designator name is used within the IBIS file, but not mapped in the IBIS instance then the name used in the EBD file will be used without mapping.

## Example

```
Example EBD File
[Ibis Ver] 3.1
[File Name] dummy.ebd
[File Rev] 0
[Source] None
[Begin Board Description] EBD1
[Manufacturer] None
[Number Of Pins] 5
[Pin List] signal_name
1 S1
N NC
3 POWER
4 GND
S S2
[Path Description] 1
Pin 1
    Len = 0.66 L = 1.33333e-08 C = 2.08333e-12 /
    Len = 2.000 L = 1e-08 C = 1.77778e-12 /
Node Comp1.1
    [Path Description] 5
Pin 5
    Len = 0.66 L = 1.33333e-08 C = 2.08333e-12 /
    Len = 2.000 L = 1e-08 C = 1.77778e-12 /
Node Comp2.1
[Reference Designator Map]
Comp1 dummy1.ibs component1
Comp2 dummy2.ibs component2
[End Board Description]
[End]
```

The preceding EBD file example is referenced in the following netlist example.

- Netlist

```
_IO_cmpnt1
+ file="dummy1.ibs"
+ component="component1"
_IO_cmpnt2
+ file="dummy2.ibs"
+ component="component2"
_IO_ebd1 file="dummy.ebd"
+ ebd_model="EBD1"
+ ref__des_map='ul=_IO_cmpnt1'
+ ref_des_map='u2=_IO_cmpnt2'
```

The above netlist instantiates two components and one EBD. The first component is located in the IBIS file dummyl.ibs and the second one in dummy2.ibs. These files are not shown
here. The EBD is located in an EBD file dummy.ebd. The EBD model used is EBD1 given within the [Begin Board Description] and [End Board Description] keywords. The ref_des_map statements inform Eldo that _IO_cmpnt1 in the netlist corresponds to Comp1 in the EBD file, and that _IO_cmpnt2 corresponds to Comp2.

## Supported Keywords and Sub-Parameters

Eldo can simulate IBIS devices either individually or in the overall component. Table 23-6 lists the supported keywords and sub-parameters in the current Eldo release. The IBISver column refers to the IBIS version in which the keyword/sub-parameter was introduced or modified.

Table 23-6. Supported Keywords and Sub-Parameters

| Keyword | Sub-parameter | IBISver |
| :---: | :---: | :---: |
| [Package] | R_pkg, L_pkg \& C_pkg | 1.0 |
| [Pin] |  |  |
|  | model_name | 1.0 |
|  | R_pin, L_pin, C_pin | 1.0 |
| [Diff Pin] |  |  |
|  | inv_pin | 2.1 |
|  | vdiff | 3.1 |
|  | tdelay_typ | 2.1 |
|  | tdelay_max | 2.1 |
|  | tdelay_min | 2.1 |
| [Voltage Range] |  | 1.0 |
| [Pullup Reference] |  | 2.1 |
| [Pulldown Reference] |  | 2.1 |
| [POWER Clamp Reference] |  | 2.1 |
| [GND Clamp Reference] |  | 2.1 |
| [Pulldown] |  | 1.0 |
| [Pullup] |  | 1.0 |
| [POWER Clamp] |  | 1.0 |
| [GND Clamp] |  | 1.0 |
| [Ramp] |  |  |
|  | dV/dt_r | 1.0 |
|  | dV/dt_f | 1.0 |

Table 23-6. Supported Keywords and Sub-Parameters

| Keyword | Sub-parameter | IBISver |
| :---: | :---: | :---: |
|  | R_load | 2.1 |
| [Rising Waveform] ${ }^{1}$ | 1000 Pts | 4.0 |
| [Falling Waveform] $^{1}$ | 1000 Pts | 4.0 |
|  | C_fixture ${ }^{2}$ | 2.0 |
|  | R_fixture | 2.0 |
|  | V_fixture | 2.0 |
|  | V_fixture_min | 2.1 |
|  | V_fixture_max | 2.1 |
| [Model] |  |  |
|  | Model_type | 4.1 |
|  | Polarity | 1.0 |
|  | Enable | 1.0 |
|  | Vinl | 2.0 |
|  | Vinh | 2.0 |
|  | C_comp ${ }^{1}$ | 1.0 |
| [Model Spec] |  |  |
|  | Vinh | 3.2 |
|  | Vinl | 3.2 |
|  | Vinh+ | 3.2 |
|  | Vinh- | 3.2 |
|  | Vinl+ | 3.2 |
|  | Vinl- | 3.2 |
| [Rgnd] |  | 2.1 |
| [Rpower] |  | 2.1 |
| [Rac] |  | 2.1 |
| [Cac] |  | 2.1 |
| [R Series] |  | 3.2 |
| [L Series] |  | 3.2 |
| [C Series] |  | 3.2 |
| [Lc Series] |  | 3.2 |

Table 23-6. Supported Keywords and Sub-Parameters

| Keyword | Sub-parameter | IBISver |
| :---: | :---: | :---: |
| [Rc Series] |  | 3.2 |
| [Series Current] |  | 3.2 |
| [Series MOSFET] |  | 3.2 |
|  | Vds | 3.2 |
| [On] |  | 3.2 |
| [Off] |  | 3.2 |
| [Series Switch Groups] | On, Off | 3.2 |
| [Series Pin Mapping] |  |  |
|  | pin_2 | 3.2 |
|  | model_name | 3.2 |
|  | function_table_group | 3.3 |
| [Model Selector] |  | 3.2 |
| [Submodel] |  |  |
|  | Submodel_type | 3.2 |
|  | Dynamic_clamp | 3.2 |
|  | Bus_hold | 3.2 |
| [Submodel Spec] |  | 3.2 |
|  | V_trigger_r | 3.2 |
|  | V_trigger_f | 3.2 |
|  | Off_delay | 3.2 |
| [GND Pulse Table] |  | 3.2 |
| [POWER Pulse Table] |  | 3.2 |
|  | V_trigger_r | 3.2 |
|  | V_trigger_f | 3.2 |
| [Pin Mapping] |  |  |
|  | pulldown_ref | 2.1 |
|  | pullup_ref | 2.1 |
|  | gnd_clamp_ref | 2.1 |
|  | power_clamp_ref | 2.1 |
| [Driver Schedule] |  |  |

Table 23-6. Supported Keywords and Sub-Parameters

| Keyword | Sub-parameter | IBISver |
| :---: | :---: | :---: |
|  | Model_name | 3.2 |
|  | Rise_on_dly | 3.2 |
|  | Rise_off_dly | 3.2 |
|  | Fall_on_dly | 3.2 |
|  | Fall_off_dly | 3.2 |
| [External Model] | [End ...] | 4.1 |
|  | Language | 4.1 |
|  | SPICE | 4.1 |
|  | Verilog-A | 4.2 |
|  | Ports | 4.1 |
|  | d_control | 4.1 |
|  | d_drive | 4.1 |
|  | d_enable | 4.1 |
|  | d_receive | 4.1 |
|  | a_puref | 4.1 |
|  | a_pdref | 4.1 |
|  | a_pcref | 4.1 |
|  | a_gcref | 4.1 |
|  | a_signal | 4.1 |
|  | d_switch | 4.1 |
|  | a_gnd | 4.1 |
|  | a_pos | 4.1 |
|  | a_neg | 4.1 |
|  | a_signal_pos | 4.1 |
|  | a_signal_neg | 4.1 |
|  | D_to_A | 4.1 |
|  | A_to_D | 4.1 |
| [External Circuit] | [End ...] | 4.1 |
| [Node Declarations] | [End ...] | 4.1 |
| [Circuit Call] | [End ...] | 4.1 |

Table 23-6. Supported Keywords and Sub-Parameters

| Keyword | Sub-parameter | IBISver |
| :---: | :---: | :---: |
|  | Signal_pin | 4.1 |
|  | Diff_signal_pins | 4.1 |
|  | Series_pins | 4.1 |
|  | Port_map | 4.1 |
| CIRCUITCALL | (reserved word) | 4.1 |
| [Package Model] |  | 2.1 |
| [Define Package Model] |  | 2.1 |
| [Manufacturer] |  | 2.1 |
| [OEM] |  | 2.1 |
| [Description] |  | 2.1 |
| [Number Of Sections] |  | 3.0 |
| [Number Of Pins] |  | 2.1 |
| [Pin Numbers] |  | 2.1 |
|  | Len | 3.0 |
|  | R | 3.0 |
|  | L | 3.0 |
|  | C | 3.0 |
|  | Fork | 3.0 |
|  | EndFork | 3.0 |
| [Model Data] | [End ...] | 2.1 |
| [Resistance Matrix] |  | 2.1 |
| [Inductance Matrix] |  | 2.1 |
| [Capacitance Matrix] |  | 2.1 |
| [Bandwidth] |  | 2.1 |
| [Row] |  | 2.1 |
|  | Banded_matrix | 2.1 |
|  | Sparse_matrix | 2.1 |
|  | Full_matrix | 2.1 |
| [Begin Board Description] |  | 3.0 |
| [Manufacturer] |  | 3.0 |

Table 23-6. Supported Keywords and Sub-Parameters

| Keyword | Sub-parameter | IBISver |
| :--- | :--- | :--- |
| [Number Of Pins] |  | 3.0 |
| [Pin List] |  | 3.0 |
|  | signal_name | 3.0 |
| [Path Description] |  | 3.0 |
|  | Len | 3.0 |
|  | R | 3.0 |
|  | L | 3.0 |
|  | C | 3.0 |
|  | Fork | 3.0 |
|  | EndFork | 3.0 |
|  | Node | 3.0 |
|  | Pin | 3.0 |
| [Reference Designator Map] |  | 3.0 |

1. Eldo ignores waveforms that have L_fixture sub-parameter with non-zero values.
2. Eldo by default ignores waveforms that have C_fixture with non-zero values, to enable using these waveforms set IBIS instance keyword C_fixture=yes.

## IBIS Tutorials

## Tutorial 1—Single-Ended Tx-Rx System

This tutorial deals with a simple arrangement of a single-ended output buffer (Tx), transmission line, and a single-ended input buffer ( Rx ). This arrangement can be used for transmission line analysis mismatch as well as to assure that the Rx correctly recognizes the logic associated with the received signal levels.

Figure 23-17. Single-Ended Tx-Rx System


The transmission line has characteristics: impedance $\mathrm{Z} 0=50 \Omega$ and signal delay $\mathrm{TD}=0.2 \mathrm{~ns}$.

## Complete Netlist

```
*Tutorial 1
_IO_Tx out d_drive
+file="tx_rx.ibs"
+component="TxRx"
+model="OUT"
TL out 0 in 0 zO=50 TD=0.2ns
_IO_Rx in d_receive
+file="tx_rx.ibs"
+component="TxRx"
+model="IN"
Rterm d_receive 0 1e6
.param VHI=1.0
.param VLO =0.0
-param TDELAY=0
.param TRISE=10p
.param TFALL=Trise
.param TSAMPLE=5n
vstim d_drive O pattern VHI VLO TDELAY TRISE TFALL TSAMPLE O 1 R
.tran 0 200n
.option step=10p
.plot tran v(out) v(d_drive) v(in) v(d_receive)
.end
```


## Netlist Explanation

```
_IO_Tx out d_drive
+file="tx_rx.ibs"
+component="TxRx"
+model="OUT"
```

The above lines instantiate an IBIS output buffer Tx with output connected to out and digital input connected to d_drive. The output buffer is located in the $t x_{-} r x$.ibs IBIS file within the TxRx component.

```
TL out O in 0 zO=50 TD=0.2ns
```

Instantiates an ideal transmission line connected between the nodes out and in with ground reference. The transmission line has $50 \Omega$ characteristics impedance and 0.2 ns time delay.

```
_IO_Rx in d_receive
+file="tx_rx.ibs"
+component="TxRx"
+model="IN"
```

Instantiates an IBIS input buffer Rx with input connected to in and its digital output connected to d_receive. The input buffer is located in the $t x \_r x$.ibs IBIS file within the TxRx component.

```
Rterm d_receive 0 1e6
```

Connects a $1 \mathrm{M} \Omega$ resistor between the digital output d_receive of the input buffer and ground. This has no impact on the results but avoids having a node with less than two connections.

```
.param VHI=1.0
.param VLO =0.0
.param TDELAY=0
-param TRISE=10p
.param TFALL=Trise
.param TSAMPLE=5n
vstim d_drive 0 pattern 1 0 0 10p 10p 5n 0 1 R
```

Instantiates the stimulus vstim for the system. The source is connected between the nodes d_drive and ground. It is defined using the pattern function with high voltage level of 1 V , low voltage level of $0 \mathrm{~V}, 0$ starting delay time, 10 ps rise and fall times, 5 ns sample time and finally it periodically alternates between 0 and 1 .

The next part of the netlist specifies the simulation control directives indicating what type of simulation Eldo should perform on the circuit.
.tran 10p 200n
Specifies a transient analysis be performed lasting 200 ns with a plotting increment of 10 ps .

```
.option step=10p
```

Imposes a time step of 10 ps .

```
    .plot tran v(out) v(d_drive) v(in) v(d_receive)
```

Specifies voltage/time plots of the voltages at nodes out, d_drive, in and d_receive.

## Simulation Results

Figure 23-18. Single-Ended Tx-Rx System Simulation Results


Ringing is clearly observed in the waveform at the receiver side. This is due to the mismatch between the TL Z0 and the Rx input impedance (ringing also means a mismatch exists between the Tx output impedance and the TL Z0). However, the Rx recognizes the signal logic levels and the digital output (d_receive) is given correctly without any undesired transitions due to the received signal ringing.

## Tutorial 2—Pseudo-Differential Tx-Rx System

This tutorial deals with a simple arrangement of a pseudo-differential output buffer (Tx), transmission line and a pseudo-differential input buffer (Rx). Same as tutorial\#1, this arrangement can be used for transmission line analysis mismatch as well as to assure that the differential Rx correctly recognizes the logic associated with the received differential signal levels.

## Complete Netlist

```
*Tutorial 2
_IO_diffout outp outn d_drive
+ file="diffsource.ibs"
+ component="diffsource"
+ pin="1" inv_pin="2"
TLp outp 0 inp 0 zO=50 TD=0.3ns
TLn outn 0 inn 0 zO=50 TD=0.3ns
_IO_diffin inp inn d_receive
+ file="diffload.ibs"
+ component="diffload"
+ pin="1" inv_pin="2"
Rterm d_receive 0 le6
.param VHI=1.0
.param VLO =0.0
.param TDELAYL=0
.param TRISE=300p
.param TFALL=Trise
.param TSAMPLE=3000p
vin D_drive O pattern VHI VLO TDELAYL TRISE TFALL TSAMPLE 1011010001 R
.tran 10p 40n
.plot tran v(d_drive) v(outp) v(outn) v(inp) v(inn) v(d_receive)
.end
```


## Netlist Explanation

```
_IO_diffout outp outn d_drive
+ file="diffsource.ibs"
+ component="diffsource"
+ pin="1" inv_pin="2"
```

The above lines instantiate an IBIS differential output buffer diffout with non-inverting output connected to outp, inverting output connected to outn and digital input connected to d_drive. The output buffer is located in the diffsource.ibs IBIS file within the diffsource component. The differential buffer is recognized from the pin and inv_pin keywords. Pin names given using these keywords must match those in the diffsource.ibs IBIS file under the [Diff_pin] keyword.

```
TLp outp 0 inp 0 ZO=50 TD=0.3ns
TLn outn 0 inn 0 zO=50 TD=0.3ns
```

Instantiates a pair of ideal transmission lines, one of them connected between the nodes outp and inp with ground reference, and the second one connected between the nodes outn and inn with ground reference. Both transmission lines have $50 \Omega$ characteristics impedance and 0.2 ns time delay.

```
_IO_diffin inp inn d_receive
+ file="diffload.ibs"
```

```
+ component="diffload"
+ pin="1" inv_pin="2"
```

Instantiates an IBIS differential input buffer diffin with non-inverting input connected to inp, inverting input connected to inn and digital output connected to d_receive. The input buffer is located in the diffload.ibs IBIS file within the diffload component. The differential buffer is recognized from the pin and inv_pin keywords. Pin names given using these keywords must match those in the diffload.ibs IBIS file under the [Diff_pin] keyword.

```
Rterm d_receive 0 le6
```

Connects a $1 \mathrm{M} \Omega$ resistor between the digital output d_receive of the input buffer and ground. This has no impact on the results avoids having a node with less than two connections.

```
.param VHI=1.0
.param VLO =0.0
-param TDELAYL=0
.param TRISE=300p
.param TFALL=Trise
.param TSAMPLE=3000p
vin d_drive O pattern VHI VLO TDELAYL TRISE TFALL TSAMPLE 1011010001 R
```

Instantiates the stimulus vin for the system. The source is connected between the nodes d_drive and ground. It is defined using the pattern function with high voltage level of 1 V , low voltage level of $0 \mathrm{~V}, 0$ starting delay time, 300 ps rise and fall times, 3 ns sample time and have the pattern 1011010001.

The next part of the netlist specifies the simulation control directives indicating what type of simulation Eldo should perform on the circuit.

```
.tran 10p 40n
```

Specifies a transient analysis be performed lasting 40 ns with a plotting increment of 10 ps .

```
.plot tran v(d_drive) v(outp) v(outn) v(inp) v(inn) v(d_receive)
```

Specifies voltage/time plots of the voltages at nodes d_drive, outp, outn, inp, inn and d_receive.

## Simulation Results

Figure 23-19. Pseudo-Differential Tx-Rx System Simulation Results


## Tutorial 3—Package Parasitics Cross Talk

This tutorial deals with the simulation of an entire component and observation of the effect of cross talk between the pins of the package. This is one of the important issues in signal integrity analysis.

## Complete Netlist

```
*Tutorial 3
_IO_Trx
+file="tx_rx.ibs"
+component="transceiver"
+package=3
vp _IO_TRX_5 0 pwl (0 0 1n 0 1.6n 3.3 8n 3.3 8.6n 0)
vCc _IO_TRX_4 0 3.3
.connect _IO_TRX_1_d_drive 0
.connect _IO_TRX_2_d_drive 0
.connect _IO_TRX_3_d_drive 0
.connect _IO_TRX_8 0
Rterm1 _IO_TRX_5_d_receive 0 1e6
Rterm2 _IO_TRX_6_d_receive 0 1e6
```

```
Rterm3 _IO_TRX_7_d_receive 0 1e6
.tran 1p 14n
.option step=1p
.plot tran v(_IO_TRX_5) v(_IO_TRX_6)
.end
```


## Netlist Explanation

```
_IO_Trx
+file="tx_rx.ibs"
+component="transceiver"
+package=3
```

The above lines instantiate an IBIS component. Component instantiation means all the buffers inside the component as well as coupling between pins can be simulated. The component is named transceiver and located in the $t x \_r x$.ibs IBIS file. The package parameter in the _IO element specifies the package modeling type to be used. In our case, package=3 means that the advanced package model, located in the $t x \_r x . i b s$ IBIS file under [Define package model] will be used.

```
vp _IO_Trx_5 0 pwl (0 0 1n 0 1.6n 3.3 8n 3.3 8.6n 0)
```

Instantiates the stimulus $\mathbf{v p}$ which is a pulse waveform connected between pin 5 of the IBIS component and ground. It is important to note that all other component pins exist in the simulation but left unconnected here. A warning will appear about these unconnected pins.

```
vCc _IO_TRX_4 0 3.3
.connect _IO_TRX_1_d_drive 0
.connect _IO_TRX_2_d_drive 0
.connect _IO_TRX_3_d_drive 0
.connect _IO_TRX_8 0
Rterm1 _IO_TRX_5_d_receive 0 1e6
Rterm2 _IO_TRX_6_d_receive 0 1e6
Rterm3 _IO_TRX_7_d_receive 0 1e6
```

The above lines have no impact on the simulation results. They are used to avoid warnings about nodes that have less than two connections. A voltage source vcc is connected between the node _IO_TRX_4 and ground. The digital inputs of the output buffers (_IO_TRX_1_d_drive, _IO_TRX_2_d_drive and _IO_TRX_3_d_drive) are tied to ground using the .connect statement. Also the node _IO_TRX_8 is connected to ground. Then $1 \mathrm{M} \Omega$ resistors are connected between the digital outputs of the input buffers (_IO_TRX_5_d_receive, _IO_TRX_6_d_receive and _IO_TRX_7_d_receive) and ground.

The next part of the netlist specifies the simulation control directives indicating what type of simulation Eldo should perform on the circuit.

```
.tran 1p 14n
```

Specifies a transient analysis be performed lasting 14 ns with a plotting increment of 1 ps .

```
.option step=1p
```

Imposes a time step of 1 ps . This small time step is imposed to capture the ringing that will occur on pin 6 due to both capacitive and inductive coupling with pin 5.

```
.plot tran v(_IO_TRX_5) v(_IO_TRX_6)
```

Specifies voltage/time plots of the voltages at both pin 5 and 6 of the IBIS component.

## Simulation Results

Figure 23-20. Package Parasitics Cross Talk


There is both capacitive and inductive coupling between pins 5 and 6 . This coupling results in a ringing effect on pin 6 .

## Tutorial 4—Simultaneous Switching Output Noise

This tutorial deals with the simulation simultaneous switching output noise (SSON). The [Pin Mapping] keyword in the IBIS file contains information on how power supplies are connected to individual buffers or groups of buffers; it can be used for predicting SSON.

Figure 23-21. Component Internal Connection


## Complete Netlist

```
*Tutorial4
_IO_comp
+file="tx_rx_pm.ibs"
+component="transceiver_pm"
+package=1
VCC _IO_comp_4 0 3.3
.connect _IO_comp_8 0
Vin1 _IO_comp_5 0 0
Vin2 _IO_comp_6 0 3.3
.param VHI=3.3
.param VLO =0.0
.param TDELAYL=1n
.param TRISE=0.1n
.param TFALL=Trise
.param TSAMPLE=5n
Vin3 _IO_comp_7 0 pattern VHI VLO TDELAYL TRISE TFALL TSAMPLE 0 1 R
.connect _IO_comp_5_d_receive _IO_comp_1_d_drive
.connect _IO_comp_6_d_receive _IO_comp_2_d_drive
.connect _IO_comp_7_d_receive _IO_comp_3_d_drive
.tran 10p 50n
.option step=10p
.plot tran v(_IO_comp_1) v(_IO_comp_2) v(_IO_comp_3)
.end
```


## Netlist Explanation

```
_IO_comp
+file="tx_rx_pm.ibs"
+component="transceiver_pm"
+package=1
```

The above lines instantiate an IBIS component. The component is named transceiver_pm and located in the $t x \_r x \_p m . i b s$ IBIS file. Package $=1$ means that package parasitics provided in the IBIS file under [Package] keyword, where package pins are assumed uncoupled, will be used.

```
vcc _IO_comp_4 0 3.3
.connect _IO_comp_8 0
```

Connects the power supply of the component. Note the user should connect the power supply manually, if the competent has a [Pin Mapping] keyword. A DC voltage source of 3.3 V is connected to pin 4 of the component and pin 8 is connected to ground.

```
vin1 _IO_comp_5 0 0
vin2 _IO_comp_6 0 3.3
.param VHI=3.3
.param VLO =0.0
.param TDELAYL=1n
.param TRISE=0.1n
.param TFALL=Trise
.param TSAMPLE=5n
vin3 _IO_comp_7 0 pattern VHI VLO TDELAYL TRISE TFALL TSAMPLE 0 1 1 0 R
```

Defines the inputs of the component input buffers. Pin 5 is connected to 0 voltage, pin 6 is connected to a DC voltage of 3.3 V and pin 7 is connected to the stimulus of the system vin3. It is defined using the pattern function with high voltage level of 3.3 V , low voltage level of 0 V , 1 ns starting delay time, 0.1 ns rise and fall times, 5 ns sample time and have the pattern 0110.

```
.connect _IO_comp_5_d_receive _IO_comp_1_d_drive
.connect _IO_comp_6_d_receive _IO_comp_2_d_drive
.connect _IO_comp_7_d_receive _IO_comp_3_d_drive
```

Connects the input buffers digital output to the output buffers digital input.
The next part of the netlist specifies the simulation control directives indicating what type of simulation Eldo should perform on the circuit.

```
.tran 10p 50n
```

Specifies a transient analysis be performed lasting 50 ns with a plotting increment of 10 ps .

```
.option step=10p
```

Imposes a time step of 10 ps .

```
.plot tran v(_IO_comp_1) v(_IO_comp_2) v(_IO_comp_3)
```

Specifies voltage/time plots of the voltages at both pin 1, 2, and 3 of the IBIS component.

## Simulation Results

Figure 23-22. Simultaneous Switching Output Noise (SSON) Simulation Results


A difference is observed in the results from the case when package $=1$ was set (compare yellow and blue waveforms). The time varying signal at OUT1 and OUT2 is not only due to IR and LdI/dt voltage drops on the supply pin, but in addition has the capacitive and inductive coupling between the package pins.

## Chapter 24 Tutorials

## Introduction

The most productive way of learning a simulation tool such as Eldo is to get 'hands-on' experience by sitting at a terminal and working through, stage by stage, a number of practical circuit simulation examples and tutorials. This chapter has been written to achieve this.

The tutorials cover a wide range of simple but concise circuit applications. Thus, they should be of interest not only to the novice user, but also to the experienced user wishing to learn more about specific simulation techniques within Eldo.

Upon completion, a wide range of techniques needed to perform efficient and productive analysis using Eldo should have been learnt.

Each tutorial starts with a brief description of the circuit in question together with a circuit diagram. A short summary of the Eldo commands used within the tutorial follows this, in order to aid users wishing to learn about a specific topic or the use of certain commands within Eldo. A complete circuit netlist is then shown, followed by a breakdown and explanation of each section. Actual output results from the circuit conclude each tutorial using EZwave, the Eldo waveform viewer.

A summary of the circuits used in this chapter, together with a brief description of the Eldo subject areas dealt with are listed below. Listings for these examples may be found in the following subdirectories included with your software:
\$MGC_AMS_HOME/examples/eldo
where \$MGC_AMS_HOME is the directory where the software resides.

## Note

For more examples please refer to the Examples appendix and "Examples for IEM" on page 1102.

Table 24-1. Tutorials

| Tutorial | Circuit Name | Eldo Description |
| :--- | :--- | :--- |
| Tutorial \#1—Parallel <br> LCR Circuit | parallel_lcr.cir | General introduction AC analysis |

Table 24-1. Tutorials

| Tutorial | Circuit Name | Eldo Description |
| :--- | :--- | :--- |
| Tutorial \#2——4th Order <br> Butterworth Filter | butterworth.cir | Transient \& AC analysis |
| Tutorial \#3—Band <br> Pass Filter | bandpass.cir | AC \& Noise analysis Model description |
| Tutorial \#4—Low Pass <br> Filter | lowpass.cir | AC analysis. Subcircuit definition |
| Tutorial \#5—Colpitts <br> Oscillator | colpitts.cir | Transient analysis. Use of model library files |
| Tutorial \#6—High <br> Voltage Cascade | hv_cascade.cir | Transient analysis. Model description |
| Tutorial \#7—Non- <br> inverting Amplifier | noninvert_amp.cir | AC \& Monte Carlo analysis. Model description |
| Tutorial \#8—Bipolar <br> Amplifier | bip_amplifier.cir | DC sensitivity analysis |
| Tutorial \#9——SC Low <br> Pass Filter | sc_lowpass.cir | Transient and small signal AC analyses using <br> the Z-domain switched capacitor models |

## Tutorial \#1—Parallel LCR Circuit

This simple circuit simulation gives a general introduction to the syntax of Eldo by performing an AC analysis on a parallel LCR circuit. The complete netlist can be found in the file parallel_lcr.cir.

Figure 24-1. Parallel LCR Circuit


Summary of Eldo Commands used in this Tutorial
. AC-AC analysis
.OPTION-Simulator configuration
.PLOT-Plot simulator results

## Complete Netlist

```
LCR Parallel Network
vin 1 0 ac 10
r2 1 2 50
r3 2 3 50k
r5 3 0 50
11 2 3 100u
c4 2 3 10n
.ac dec 10 1 1g
.option eps = 1.0e-6
.plot ac vdb(2) vdb(3) (-30,20)
.end
```


## Netlist Explanation

```
LCR Parallel Network
```

The above line is the circuit title. It must always be the first line of a simulation.
The first part of the Eldo netlist is a description of the circuit components.

```
vin 1 0 ac 10
```

The above line defines an AC voltage source vin connected between the nodes 1 and 0 of value 10 V .

```
r2 1 2 50
r3 2 3 50k
r5 3 0 50
11 2 3 100u
c4 2 3 10n
```

The above lines define the devices present in the circuit to be simulated. Each device instantiation gives the component name, the nodes to which the component is connected and the value of the component.

The next part of the netlist specifies the simulation control directives indicating what type of simulation Eldo should perform on the circuit.

```
.ac dec 10 1 1g
```

The above line indicates that an AC analysis should be performed on the circuit within the frequency range 1 Hz to 1 GHz with 10 steps per decade.

```
.option eps = 1.0e-6
```

The above line increases the internal accuracy of Eldo from its default value of 5 mV to $1 \mu \mathrm{~V}$. This is very important to achieve the best results for the simulation of most analog circuits.

```
.plot ac vdb(2) vdb(3) (-30,20)
```

The above line specifies a $\mathrm{dB} /$ frequency plot of the nodes 2 and 3 on the same graph between the limits -30 dB and +20 dB . The results are stored in the parallel_lcr. $w d b$ file and can be displayed using the EZwave graphical results post-processor.
.end

The netlist must always be terminated with the above command.

## Simulation Results

Figure 24-2. Tutorial \#1—Simulation Results


## Tutorial \#2—4th Order Butterworth Filter

This example simulates a 4th order Butterworth filter with a transient and an AC analysis being performed on the circuit. The complete netlist can be found in the file butterworth.cir.

Figure 24-3. 4th Order Butterworth Filter


```
Summary of Eldo Commands used in this Tutorial
    . AC-AC analysis
    .PLOT-Plot simulator results
    .TRAN-Transient analysis
```


## Complete Netlist

```
4th Order Butterworth Filter
c1 4 0 1.5307n
c2 3 0 1.0824n
11 3 4 1.5772u
12 2 3 .38268u
r1 1 2 1
v1 1 0 ac 1 pwl (0 0 1u 0 2u 1 20u 1 20.1u 0)
.tran . 2u 40u
.plot tran v(4) (-1,1.5)
.plot tran v(1) (0,1.5)
.ac dec 20 10000 100meg
.option eps=1.0e-6 be
.plot ac vdb(4) (-120,40)
.plot ac vp(4) (-200,200)
.end
```


## Netlist Explanation

```
4th Order Butterworth Filter
c1 4 0 1.5307n
c2 3 0 1.0824n
l1 3 4 1.5772u
12 2 3 .38268u
r1 1 2 1
v1 1 0 ac 1 pwl (0 0 1u 0 2u 1 20u 1 20.1u 0)
```

The above line defines an AC source of 1 V and a time dependent Piece Wise Linear function between the nodes 1 and 0 . The pwl parameters describe a signal that stays at 0 V until $1 \mu \mathrm{~s}$ where it rises to 1 V in $1 \mu \mathrm{~s}$. The signal stays at 1 V until $20 \mu \mathrm{~s}$ where it drops back to 0 V in $0.1 \mu \mathrm{~s}$.
i Refer to the output results for a pictorial representation of this signal.
.tran . 2u 40u
The above line specifies that a transient analysis should be performed on the circuit lasting $40 \mu \mathrm{~s}$ with a plotting increment for the line printer of $0.2 \mu \mathrm{~s}$.

```
.plot tran v(4) (-1,1.5)
.plot tran v(1) (0,1.5)
```

The above lines specify that voltage/time plots should be performed on separate graphs of the voltage at node 4 between the limits -1 and +1.5 V , and of the voltage at node 1 between the limits 0 and +1.5 V .

```
.ac dec 20 10000 100meg
```

The above line indicates that an AC analysis should be performed on the circuit within the frequency range 10000 Hz to 100 MHz with 20 steps per decade. This AC analysis statement replaces the transient analysis definition found earlier in the netlist.

```
.option eps=1.0e-6 be
```

The above line sets the simulator accuracy together with the simulator algorithm as Backward Euler.

```
.plot ac vdb(4) (-120,40)
.plot ac vp(4) (-200,200)
```

The above lines specify that $\mathrm{dB} /$ frequency and phase/frequency plots should be performed of the voltage at node 4 between the limits -120 dB and +40 dB and -200 and +200 degrees respectively. These commands are added to the first simulation run netlist. The results are also added to the file butterworth. $w d b$ and can be displayed as a second simulation page using the EZwave graphical post-processor.

## Simulation Results-1

Figure 24-4. Tutorial \#2—Simulation Results-1


Tutorials

## Simulation Results-2

Figure 24-5. Tutorial \#2—Simulation Results-2


## Tutorial \#3—Band Pass Filter

This tutorial deals with an op-amp band pass filter. The simulation performs an AC analysis of the circuit, together with a noise analysis of the output stage of the filter. The complete netlist can be found in the file bandpass.cir.

Figure 24-6. Band Pass Filter


[^12]Summary of Eldo Commands used in this Tutorial

## Complete Netlist

```
Band-Pass filter
.model ampop modfas gain=10000.0 p1=5e3
r1 1 3 10k
r2 3 5 10k
r3 2 4 13.95k
r4 2 0 7.79k
r5 6 0 10k
r6 4 6 3.9k
r7 4 7 244.7k
r8 7 9 10k
r9 8 0 5k
r10 7 0 10.43k
r11 11 0 10k
r12 11 10 8.87k
r13 10 0 50
c1 1 2 3.27n
c2 2 0 16.73n
c3 2 5 20n
c4 3 4 40n
c5 4 8 3.17n
c6 8 0 9.5n
c7 8 9 12.7n
c8 7 10 25.3n
y1 opamp2 pin: 5 6 4 0 model: ampop
y2 opamp2 pin: 9 11 10 0 model: ampop
v1 1 0 ac
.ac dec 80 100 10k
.noise v(10) v1 80
.plot noise db(inoise)
.plot noise db(onoise)
.plot ac vdb(10) (10,-50)
.end
```


## Netlist Explanation

```
Band-Pass filter
.model ampop modfas gain=10000.0 p1=5e3
```

The above line describes the electrical parameters of the user defined model ampop based on the opamp2 macromodel. The gain (gain) and dominant pole frequency ( $\mathbf{p}$ ) of the model are set to 10000 and $5 \times 10^{3} \mathrm{~Hz}$.

1. For more details on the opamp2 macromodel and its parameters, refer to Analog
Macromodels.
```
v1 1 0 ac
r1 1 3 10k
r2 3 5 10k
r3 2 4 13.95k
r4 2 0 7.79k
r5 6 0 10k
r6 4 6 3.9k
r7 4 7 244.7k
r8 7 9 10k
r9 8 0 5k
r10 7 0 10.43k
r11 11 0 10k
r12 11 10 8.87k
r13 10 0 50
c1 1 2 3.27n
c2 2 0 16.73n
c3 2 5 20n
c4 3 4 40n
c5 4 8 3.17n
c6 8 0 9.5n
c7 8 9 12.7n
c8 7 10 25.3n
yopa1 opamp2 pin: 5 6 4 0 model: ampop
yopa2 opamp2 pin: 9 11 10 0 model: ampop
```

The above lines instantiate two operational amplifiers yopa1 and yopa2 of macromodel type opamp2 (linear 2-pole) connected between the nodes 5, 6, 4 and 0 and between the nodes 9 , 11,10 and 0 respectively. The electrical parameters of the macromodel are defined in the model ampop.

```
.ac dec 80 100 10k
```

The above line indicates that an AC analysis should be performed on the circuit within the frequency range 100 Hz to 10 kHz with 80 steps per decade.

```
.noise v(10) v1 80
```

The above line indicates that a noise analysis should be performed of the voltage at node 10 with the voltage source v1 as input noise voltage. The analysis should be averaged over 80 frequency points.

```
.plot noise db(inoise)
.plot noise db(onoise)
.plot ac vdb(10) (10,-50)
```

The above lines specify a $\mathrm{dB} /$ frequency plot to be performed on the input and output noise, together with a $\mathrm{dB} /$ frequency plot of the voltage at node 10 , the output stage of the filter, between the limits 10 and -50 dB .

Tutorials
Tutorial \#3—Band Pass Filter

## Simulation Results

Figure 24-7. Tutorial \#3—Simulation Results


## Tutorial \#4—Low Pass Filter

This tutorial deals with the AC analysis of a low pass filter which incorporates a voltage amplifier, illustrating the use of Eldo's subcircuit capabilities, as the voltage amplifier part of the circuit itself is defined in this manner. The complete netlist can be found in the file lowpass.cir.

Figure 24-8. Low Pass Filter


```
Summary of Eldo Commands used in this Tutorial
.AC-AC analysis
.MODEL-Model definition
.PLOT-Plot simulator results
.SUBCKT-Subcircuit definition
```


## Complete Netlist

```
Low Pass Filter incorporating a Voltage Amplifier
* .MODEL definition
.model q2n2222 npn is=1.9e-14 bf=150 vaf=100 ikf=.175
+ ise=5e-11 ne=2.5 br=7.5 var=6.38 ikr=.012 isc=1.9e-13
+ nc=1.2 rc=.4 cje=26p tf=.5e-9 cjc=11p tr=30e-9 xtb=1.5
+ kf=3.2e-16 af=1.0
* Subcircuit definition
.subckt amp in out vdd
c30 in 31 47u
r30 31 33 390
r31 vdd 33 50k
r32 33 0 15k
q30 out 33 0 q2n2222
r33 vdd out 750
.ends amp
```

```
r1 1 2 10
11 2 3 1.3m
c1 3 0 100n
r2 4 0 50k
x1 3 4 9 amp
vb 9 0 5
v1 1 0 ac 1
* Commands
.ac dec 10 1 1g
.plot ac vdb(3) vdb(4) (-250,50)
.plot ac vp(3) vp(4) (-200,200)
.end
```


## Netlist Explanation

```
Low Pass Filter incorporating a Voltage Amplifier
.model q2n2222 npn is=1.9e-14 bf=150 vaf=100 ikf=.175
+ ise=5e-11 ne=2.5 br=7.5 var=6.38 ikr=.012 isc=1.9e-13
+ nc=1.2 rc=.4 cje=26p tf=.5e-9 cjc=11p tr=30e-9 xtb=1.5
+ kf=3.2e-16 af=1.0
.subckt amp in out vdd
```

The above line indicates the start of the voltage amplifier subcircuit definition. The subcircuit is called amp and is connected between the nodes in, out and vdd.

```
c30 in 31 47u
r30 31 33 390
r31 vdd 33 50k
r32 33 0 15k
r33 vdd out 750
q30 out 33 0 q2n2222
.ends amp
```

The above line indicates the end of the definition of the subcircuit amp.

## Note

All nodes used within the subcircuit are local nodes, in that they are only referenced within the subcircuit itself and that they do not have to correspond with the names of the nodes outside the subcircuit.

```
r1 1 2 10
r2 4 0 50k
11 2 3 1.3m
c1 3 0 100n
x1 3 4 9 amp
```

The above line instantiates the subcircuit $\mathbf{x} 1$ of type amp connected between the nodes 3,4 , and 9 . As explained earlier, these nodes correspond to the nodes in, out and vdd within the subcircuit.

```
vb 9 0 5
v1 1 0 ac 1
```

The above lines define the voltage sources in the circuit. An AC voltage source v1 connected between the nodes 1 and 0 of value 1 V and a DC voltage source between the nodes 9 and 0 of value 5 V .

```
.ac dec 10 1 1g
.plot ac vdb(3) vdb(4) (-250,50)
.plot ac vp(3) vp(4) (-200,200)
. end
```


## Simulation Results

Figure 24-9. Tutorial \#4—Simulation Results


## Tutorial \#5—Colpitts Oscillator

This tutorial deals with the transient analysis of a simple oscillator circuit. It also illustrates making use of model library files found elsewhere in the system environment. The complete netlist can be found in the file colpitts.cir.

Figure 24-10. Colpitts Oscillator


```
Summary of Eldo Commands used in this Tutorial
.MODEL-Model definition
.OPTION-Simulator configuration
.PLOT-Plot simulator results
.TRAN-Transient analysis
```


## Complete Netlist

.model definition in the library file: nBJt_LIB

```
.model ts2 npn
+ bf=10 br=1 xtb=3 is=10f eg=1.11 rb=100
+ rc=10 vaf=50 tr=6n mjc=0.75 mje=0.33 vje=0.75
```


## Main Eldo Netlist

```
Colpitts Oscillator
l1 1 3 5u
c1 1 2 2n
c2 2 3 100p
r3 2 4 2200
q1 3 0 2 ts2
v1 1 0 5
v2 4 0 -5
i1 2 4 pulse(0 10u 0 5n 5n 25n 50n)
```

```
.model lib nbjt_lib ts2
.option eps=1.0e-6
.tran 1u 12u
.plot tran v(1,3) (10,-10)
.end
```


## Netlist Explanation

. model definition in the library file nbJt_lib:

```
.model ts2 npn
bf=10 br=1 xtb=3 is=10f eg=1.11 rb=100
rc=10 vaf=50 tr=6n mjc=0.75 mje=0.33 vje=0.75
```

The above lines describe the electrical parameters of the npn transistor model ts2.

## Main Eldo Netlist

$$
\begin{array}{llll}
\mathbf{l} & 1 & 3 & 5 \mathrm{u} \\
\mathbf{c} 1 & 1 & 2 & 2 \mathrm{n} \\
\mathbf{c} 2 & 2 & 3 & 100 \mathrm{p} \\
\mathbf{r} 3 & 2 & 4 & 2200 \\
\mathbf{q} 1 & 3 & 0 & 2
\end{array} \mathrm{ts} 2
$$

The above line defines a transistor q1 between nodes 3,0 and 2 with electrical parameters defined by the model ts2.
v1 1105
v2 $4 \quad 0 \quad-5$
The above lines define the voltage sources in the circuit. A DC voltage source v1 connected between the nodes 1 and 0 of value 5 V and also a DC voltage source between the nodes 4 and 0 of value -5 V .
i1 24 pulse (0 10u 0 5n 5n 25n 50n)
This line defines a time dependent pulse function between nodes 2 and 4 describing the following signal:

0 A at 0 s (delay time is 0 s )
0 A to $10 \mu \mathrm{~A}$ in a rise time of 5 ns
$10 \mu \mathrm{~A}$ from 5 to 30 ns (pulse width is 25 ns )
$10 \mu \mathrm{~A}$ to 0 A in a fall time of 5 ns
0 A at 35 ns
Cycle repeats starting from 50 ns .
.MODEL LIB NBJT_LIB TS2

The above line indicates that the electrical parameters of the model TS2 are defined in the library file NBJT_LIB as shown previously.

```
.option eps=1.0e-6
.tran 1u 12u
```

The above specifies a transient analysis is to be performed lasting $12 \mu \mathrm{~s}$ with a plotting increment of $1 \mu \mathrm{~s}$.

$$
\text { .plot tran } v(1,3) \quad(10,-10)
$$

The above line specifies a voltage/time plot to be performed of the voltage difference between the nodes 1 and 3 between the limits $\pm 10 \mathrm{~V}$.

## Simulation Results

Figure 24-11. Tutorial \#5-Simulation Results


## Tutorial \#6-High Voltage Cascade

This tutorial deals with the transient analysis of a high voltage cascade circuit. The complete netlist can be found in the file $h v_{-} c a s c a d e . c i r$.

Figure 24-12. High Voltage Cascade


```
Summary of Eldo Commands used in this Tutorial
.MODEL-Model definition
.OPTION-Simulator configuration
.PLOT-Plot simulator results
.TRAN-Transient analysis
.PARAM-Global parameter setting
```


## Complete Netlist

```
high voltage cascade
.model dl1001 d rs=10 vj=0.8
d1 1 2 dl1001
d2 2 3 dl1001
d3 3 4 dl1001
d4 4 5 dl1001
d5 5 6 dl1001
c1 2 0 cap1
c2 1 3 cap1
c3 2 4 cap1
c4 3 5 cap1
c5 4 6 cap1
c6 5 0 cap2
vin 1 0 sin(0 2500 50k 0 0)
.param cap1=1n cap2=10n
.option reltol=0.01 vmax =100000 vmin=-100000
.tran 0.5m 5m
.plot tran v(5)
-plot tran v(1)
.end
```


## Netlist Explanation

```
high voltage cascade
.model dl1001 d rs=10 vj=0.8
```

The above line describes the electrical parameters of the diode model dl1001.

## i <br> For a detailed description of each of these parameters, refer to the Device Models chapter.

```
d1 1 2 dl1001
d2 2 3 dl1001
d3 3 4 dl1001
d4 4 5 dl1001
d5 5 6 dl1001
c1 2 0 cap1
c2 1 3 cap1
c3 2 4 cap1
c4 3 5 cap1
c5 4 6 cap1
c6 5 0 cap2
vin 0 1 sin(0 2500 50k 0 0)
```

The above line defines a sinusoidal function between the nodes 1 and 0 , with a starting amplitude of 2500 V and a frequency of 50 kHz .

```
.param cap1=1n cap2=10n
```

The above line defines the global parameters cap1 and cap2 that are used in the capacitor and diode definitions to be 1 nF and 10 nF respectively.

```
.option reltol=0.01 vmax=100000 vmin=-100000
```

The above line sets the relative accuracy to a value of 0.01 and output voltage limits between 100,000 and $-100,000 \mathrm{~V}$ due to the high voltage levels present in this circuit.

```
.tran 0.5m 5m
```

The above line specifies that a transient analysis should be performed on the circuit lasting 5 ms with a plotting increment for the line printer of 0.5 ms .

```
.plot tran v(5)
plot tran v(1)
```

The above lines specify voltage/time plots to be performed on separate graphs of the voltages at nodes 5 and 1.

## Simulation Results-1

Figure 24-13. Tutorial \#6-Simulation Results—1


## Simulation Results-2

Figure 24-14. Tutorial \#6—Simulation Results-2


## Tutorial \#7—Non-inverting Amplifier

This tutorial deals with Monte Carlo analysis on a non-inverting amplifier circuit. A specified number of simulation runs are carried out to see the effect on the circuit of changing component values within a specified range during each simulation run. Upper and lower limits of the outputs are then displayed by Eldo at the end of the simulation. The complete netlist can be found in the file noninvert_amp.cir.

Figure 24-15. Non-inverting Amplifier


```
Summary of Eldo Commands used in this Tutorial
    .AC-AC analysis
    .MC-Monte Carlo analysis
    .MODEL-Model definition
    .OPTION-Simulator configuration
    .PLOT-Plot simulator results
```


## Complete Netlist

```
Non-Inverting Amplifier
.model modres res lot=50% dev=60%
r1 5 3 modres 100k
r2 5 0 modres 1k
c1 3 0 1p
yopa opamp2 pin : 2 5 3 0 param: p1=1e3 p2=5e8 gain=5000
vin1 2 0 ac
.ac dec 30 1.0 100meg
.option eps=1.0e-6
.mc 7 vdb(3)
.print ac vdb(3)
.plot ac vdb(3) (-40,60)
.plot ac vp(3) (0,-90)
.end
```


## Netlist Explanation

```
Non-inverting amplifier
.model modres res lot=50% dev=60%
```

The above line specifies the Monte Carlo parameter limits for resistor model type modres. It indicates that for each Monte Carlo run the resistor values can change together by as much as $50 \%$ (lot tolerance). Additionally, the resistor values are allowed to change independently of each other by as much as $60 \%$ (dev tolerance). As can be seen below, these limits will have a more profound effect on the resistor $\mathbf{r} 2$ than that of $\mathbf{r}$.

```
r1 5 3 modres 100k
r2 5 0 modres 1k
c1 3 0 1p
```

The above lines give the information of the resistors and capacitors that are present in the circuit to be simulated. Listed is the component name, the nodes between which the component is connected and the value of the component.

## Note

The resistors are also defined to be of model type modres. This is present in order to specify Monte Carlo parameter limits for the resistors during the simulation runs.

```
yopa opamp2 pin: 2 5 3 0 param: p1=1e3 p2=5e8 gain=5000
vin1 2 0 ac
.ac dec 30 1.0 100meg
.option eps=1.0e-6
.mc 7 vdb(3)
```

The above line indicates that seven Monte Carlo simulation runs should be carried out on the voltage at node 3 . The plotted output results contain nominal simulation results without any change in the circuit values, together with highest and lowest deviation results over the seven simulation runs.

```
.print ac vdb(3)
.plot ac vdb(3) (-40,60)
.plot ac vp(3) (0,-90)
.end
```

For more information on Monte Carlo analysis, refer to ".MC" on page 706.

## Simulation Results

Figure 24-16. Tutorial \#7-Simulation Results


## Tutorial \#8-Bipolar Amplifier

This tutorial deals with a DC sensitivity analysis on the output of a bipolar amplifier circuit. The results show us which DC components have the most effect on the output of the circuit if they were to be changed. The complete netlist can be found in the file bip_amplifier.cir.

Figure 24-17. Bipolar Amplifier


```
Summary of Eldo Commands used in this Tutorial
.MODEL-Model definition
.SENS-Sensitivity analysis
```


## Complete Netlist

```
bipolar amplifier
.model tun1 npn rb=524 irb=0.0 rbm=25 rc=150 re=1.0
+ is=121e-18 eg=1.206 xti=2 xtb=1.538 bf=137 ikf=6.9e-3
+ nf=1 vaf=159 ise=36e-16 ne=1.7 br=0.7 ikr=2.2e-3
+ nr=1 var=10.7 isc=0.0 nc=2 tf=0.6e-9 tr=54.e-9
+ cje=0.2e-12 vje=0.5 mje=0.24 cjc=1.8e-13 vjc=0.5
+ mjc=0.3 xcjuc=0.3 cjs=1.3e-12 vjs=0.7 mjs=0.2 fc=0.9
+ itf=40.e-3 vtf=10 xtf=7
r1 2 0 6.8k
r2 3 2 100k
r3 3 4 1.8k
r4 5 0 100
ra 6 0 2.2k
c1 1 2 0.47u
c2 4 6 1u
q1 4 2 5 tun1
v1 1 0 0
v2 3 0 24
.sens v(4)
.end
```


## Netlist Explanation

```
bipolar amplifier
.model tun1 npn rb=524 irb=0.0 rbm=25 rc=150 re=1.0
+ is=121e-18 eg=1.206 xti=2 xtb=1.538 bf=137 ikf=6.9e-3
+ nf=1 vaf=159 ise=36e-16 ne=1.7 br=0.7 ikr=2.2e-3
+ nr=1 var=10.7 isc=0.0 nc=2 tf=0.6e-9 tr=54e-9
+ cje=0.2e-12 vje=0.5 mje=0.24 cjc=1.8e-13 vjc=0.5
+ mjc=0.3 xcjc=0.3 cjs=1.3e-12 vjs=0.7 mjs=0.2 fc=0.9
+ itf=40.e-3 vtf=10 xtf=7
r1 2 0 6.8k
r2 3 2 100k
r3 3 4 1.8k
r4 5 0 100
ra 6 0 2.2k
c1 1 2 0.47u
c2 4 6 1u
q1 4 2 5 tun1
v1 1 0 0
v2 3 0 24
.sens v(4)
```

The above line indicates that a DC sensitivity analysis should be performed showing the relative sensitivities that the DC components have on the voltage on node 4 , the output node of the amplifier. The results are listed in the bip_amplifier.chi file.
. end

The results of the sensitivity analysis, found in the bip_amplifier.chi file, are listed overleaf.

## Simulation Results

Figure 24-18. Tutorial \#8-Simulation Results

| $\begin{gathered} \text { DC SENSITIVITIES } \\ \text { ELEMENT } \\ \text { NAME } \end{gathered}$ | OUTPUT V(4) ELEMENT VALUE | ELEMENT SENSITIVITY (VOLTS/UNIT) | NORMALIZED SENSITIVITY (VOLTS/PERCENT) |
| :---: | :---: | :---: | :---: |
| R1 | $6.800 \mathrm{E}+03$ | -1.39E-03 | -9.45E-02 |
| R2 | $1.000 \mathrm{E}+05$ | $1.180 \mathrm{E}-04$ | $1.180 \mathrm{E}-01$ |
| R3 | $1.800 \mathrm{E}+03$ | -3.90E-03 | -7.02E-02 |
| R4 | $1.000 \mathrm{E}+02$ | $3.297 \mathrm{E}-02$ | $3.297 \mathrm{E}-02$ |
| RA | $2.200 \mathrm{E}+03$ | $0.000 \mathrm{E}+00$ | $0.000 \mathrm{E}+00$ |
| V1 | $0.000 \mathrm{E}+00$ | $0.000 \mathrm{E}+00$ | $0.000 \mathrm{E}+00$ |
| V2 | $2.400 \mathrm{E}+01$ | $4.585 \mathrm{E}-01$ | $1.100 \mathrm{E}-01$ |
| Q1 |  |  |  |
| RB | $3.489 \mathrm{E}+02$ | $3.689 \mathrm{E}-04$ | $1.287 \mathrm{E}-03$ |
| RC | $1.500 \mathrm{E}+02$ | $9.155 \mathrm{E}-05$ | 1.373E-04 |
| RE | $1.000 \mathrm{E}+00$ | $3.297 \mathrm{E}-02$ | $3.297 \mathrm{E}-04$ |
| BF | $1.370 \mathrm{E}+02$ | -1.82E-02 | -2.49E-02 |
| JLE/ISE | $3.600 \mathrm{E}-15$ | $6.409 \mathrm{E}+12$ | $2.307 \mathrm{E}-04$ |
| BR | $7.000 \mathrm{E}-01$ | $1.394 \mathrm{E}-11$ | $9.759 \mathrm{E}-14$ |
| JLC/ISC | $0.000 \mathrm{E}+00$ | $0.000 \mathrm{E}+00$ | $0.000 \mathrm{E}+00$ |
| JS/IS | $1.210 \mathrm{E}-16$ | $-1.93 \mathrm{E}+15$ | -2.34E-03 |
| NLE | $1.700 \mathrm{E}+00$ | -2.52E-01 | -4.28E-03 |
| NLC | $2.000 \mathrm{E}+00$ | $0.000 \mathrm{E}+00$ | $0.000 \mathrm{E}+00$ |
| JBF / IKF | $6.900 \mathrm{E}-03$ | -1.43E+02 | -9.87E-03 |
| JBR/IKR | $2.200 \mathrm{E}-03$ | $2.771 \mathrm{E}-11$ | $6.095 \mathrm{E}-16$ |
| VBF | $1.590 \mathrm{E}+02$ | $2.163 \mathrm{E}-03$ | $3.439 \mathrm{E}-03$ |
| VBR | $1.070 \mathrm{E}+01$ | -2.60E-02 | -2.78E-03 |

Referring to the above results, the element sensitivity is the change in the output of interest (in this case the voltage at node 4) due to a one unit change in the value of the element of interest (for example $\mathbf{r} 1$ ) and the normalized sensitivity is the change in the output of interest due to a one percent change in the value of the element of interest.

Looking at the sensitivity output in normalized sensitivity (volts/percent), it can be seen that the output at node 4 is most sensitive to the voltage source $\mathbf{v} 2$ and also to the bf parameter in q1. As a result, variation in these values causes a significant effect on the output voltage.

Please refer to ".SENS" on page 863.

## Tutorial \#9—SC Low Pass Filter

This example deals with the transient \& small signal AC analysis of an SC low pass filter using the Z-domain switched capacitor models. The complete netlist can be found in the file sc_lowpass.cir.

```
Summary of Eldo Commands used in this Tutorial
    . AC-AC analysis
    .PLOT-Plot simulator results
    .TRAN-Transient analysis
```


## Complete Netlist

```
SC_lpfilt.cir
.param ts = 1.000000e-05
.subckt sc_int inp inm out
y1 sc_ideal inp inm out
y2 sc_u inm out param: c=c tp=tp
.ends sc_int
* INTEGRATOR 1
xi01 0 501 1 SC_INT c=5.173415p tp=ts
y002 sc_n pin: 2 0 501 0 param: c=1.347451p tp=ts
y003 sc_n pin: INPUT 0 501 0 param: c=1.623277p tp=ts
y004 sc_n pin: 1 0 501 0 param: c=1.000000p tp=ts
* INTEGRATOR 2
xi05 0 502 2 sc_int c=5.839726p tp=ts
y006 sc_i pin: 1 0 502 0 param: c=1.232076p tp=ts ldi=2
y007 sc_i pin: 3 0 502 0 param: c=1.000000p tp=ts ldi=2
* INTEGRATOR 3
xi08 0 503 3 sc_int c=4.117249p tp=ts
y009 sc_n pin: 2 0 503 0 param: c=1.660161p tp=ts
y010 sc_n pin: 3 0 503 0 param: c=1.000000p tp=ts
.tran 1u 500u
.ac dec 500 100 1meg
.plot tran v(input)
-plot tran v(1)
.plot tran v(2)
.plot tran v(3)
.plot ac vdb(1)
.plot ac vdb(2)
.plot ac vdb(3)
vin input 0 dc 1.0 ac 1.0 pwl(0.0 0.0 10n 1.0)
.end
```


## Simulation Results-1

Figure 24-19. Tutorial \#9—Simulation Results-1


## Simulation Results-2

Figure 24-20. Tutorial \#9—Simulation Results—2


Tutorials
Tutorial \#9—SC Low Pass Filter

## Chapter 25 Simulator Compatibility

## Introduction

Eldo provides compatibility with different simulators. Eldo can use an external simulator netlist as input, accepting the different constructs and syntax used by such simulators. This chapter shows the compatibility available. It is divided into the following sections:

- HSPICE Compatibility
- TIspice Compatibility
- Spectre Compatibility


## HSPICE Compatibility

Eldo provides partial compatibility with HSPICE ${ }^{\circledR 1}$. Eldo can use an HSPICE netlist as input. Eldo HSPICE compatibility is invoked as follows:

```
eldo -compat ... cir_file_name
```

or by adding in the netlist the following option (must be set at the top of the design):

```
.OPTION COMPAT
```

The main effect is that it accepts some HSPICE constructs and syntax. This section shows the different effects that this compatibility mode has. It is divided into the following:

- Devices
- Commands
- Options
- Netlist
- Arithmetic Functions and Operators
- Output Format

Additional flexibility is offered. Instead of using -compat, the flags -compmod and -compnet can be set with the following effects:

[^13]-compmod Triggers only the automatic conversion of models (can alternatively be set with . OPtion COMPMOD); see Devices.
-compnet Causes the netlist to be interpreted as compatible format, but the models themselves are treated as Eldo Spice models. This means it is assumed that models are already Eldo models (for example, to select the BSIM3v3 model the level specified must be 53 , not 49); (-compnet can alternatively be set with . OPTION COMPNET).

Note $\qquad$
The -compnet and -compmod flags apply to the entire netlist, including library files. For example, this implies that when compnet is set, even the statements in the library file, including those of model library files, are interpreted in -compat mode.

## Note



Flag -compat (or .OPtion COMPAT) is equivalent to setting both -compmod and -compnet flags (or .OPtion COMPMOD and .OPtion COMPNET).

## Devices

## Eldo Levels

The following Eldo Levels are set:
Table 25-1. MOS Levels with -compat

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
| 2 | Eldo2 (Eldo LEVEL 12) |
| 3 | Eldo3 (Eldo LEVEL 13) |
| 6 | Modified Lattin-Jenkins Grove Model (Eldo LEVEL 16) |
| 8 | Enhanced Berkeley LEVEL 2 (Eldo LEVEL 17) |
| 13 | Berkeley BSIM1 (Eldo LEVEL 8) |
| 39 | Berkeley BSIM2 (Eldo LEVEL 11) |
| 49 | Berkeley BSIM3 v3.0 \& BSIM3 v3.1 (Eldo LEVEL 53) |
| 50 | Philips MOS Model 9 (Eldo LEVEL 59) |
| 54 | Berkeley BSIM4.0.0 (Eldo LEVEL 60) |
| 57 | Berkeley BSIMSOI3v2 PD (Eldo LEVEL 56, SOIMOD=1) |
| 59 | Berkeley BSIMSOI3v2 FD (Eldo LEVEL 56, SOIMOD=3) |
| 68 | HiSIM Model (Eldo LEVEL 66) |

Table 25-1. MOS Levels with -compat

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
| 70 | BSIMSOIv4 Model (Eldo LEVEL 72) |

For more information see "MOS Levels with -compat" on page 255.

Table 25-2. BJT Models with -compat

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
| 2 | Improved Berkeley Model (Eldo LEVEL 5) |
| 3 | STMicroelectronics LEVEL 1 (Eldo LEVEL 2) |
| 4 | VBIC v1.2 (Eldo LEVEL 8) |
|  | (VERSION=1.15) VBIC v1.1.5 (Eldo LEVEL 8) |
| 6 | Philips Mextram 503.2 Model (Eldo LEVEL 4) |
| 8 | HICUM Model (Eldo LEVEL 9) |

For more information, see "BJT Models with -compat" on page 236.

Table 25-3. Diode Models with -compat

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
| 2 | Fowler-Nordheim (Eldo LEVEL 3) |
| 3 | Berkeley Level 1 (Eldo LEVEL 1), by default SCALEV is set to 3 |
| 4 | JUNCAP Diode Model (Eldo LEVEL 8), by default DIOLEV is set to 9 |

For more information, see "Using -compat with Diodes" on page 229.

Table 25-4. Resistor Level with -compat

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
| 1 | RC Wire (Eldo LEVEL 3) |

1 For more information, see "RC Wire Model Syntax" on page 150.

## PNP and NPN devices

The -compat flag affects the default type for PNP and NPN devices. subs defines the type of BJT. By default, NPN and PNP are vertical:

If subs is -1 , BJT is lateral.
If subs is 1, BJT is vertical.
If -compat is set, NPN are vertical, PNP are lateral.
For more information, see "BJT Model Syntax" on page 235.

## Group Delay

Vt is equivalent to VGD, and It is equivalent to IGD (Group Delay on voltage or current). For more information, see "VXxx (devname.posi)" on page 800.

## Node GROUND/GND/GND!

Node Ground, GND and GND! are assumed to be the global node 0 .

## Value "x"

" $x$ " is equivalent to "meg", i.e. when the -compat flag is set:
R1 10 1x
is equivalent to:

R1 10 1meg
Otherwise, 1x corresponds to 1.0 .

## Commands

- .ALTER

This command is cumulative. For example:

```
r1 1 0 1
r2 2 0 1
.alter 1
r1 1 0 2
.alter 2
r2 2 0 2
```

The second "alter" simulation will be done with both r1 set to 2 (inheritance from later number 1), and r2 set to 2 . For more information see ".ALTER" on page 549.

Option compat can be placed anywhere in the netlist; it is not order-dependent. However, if the netlist contains .ALTER statements, and the option is placed in the .alter block then it will not be taken into account in the nominal run, only the .ALTER run. Then it will remain active for any further .ALTER runs. For example, if the netlist contains:

```
title
netlist
.alter 1
.option compat
.alter 2
...
.end
v1 1 0 1
r1 1 0 1
.dc
.end
```

Here, the nominal run will not recognize the compat option, the first .alter will, and the second .alter will also. The statements between the last two .end statements, which correspond to the simulation of yet another circuit, will still consider compat as active. Once activated, compat cannot be deactivated.

- .DC

When only a DC analysis is specified in conjunction with the -compat flag, by default the initial transient value will be used. For more information see ".DC" on page 588.

- .HDL

The syntax is different with the -compat flag:

```
.HDL "filename" [module_name] [module_alias]
```

See also ".HDL" on page 678.

- .LIB
. lib behaves as . Include. For more information see ".LIB" on page 692.
- .PLOT/.PRINT

The sign convention of $\mathrm{I}_{\mathrm{x}}$ is that the current is positive when it enters the device by pin x . However, when -compat is set, then the following apply:
For R/L/C/E/F/G/H/I/V/D devices, 12 returns the same value as I 1 .
For M/B/J devices, $\mathbf{I 3}$ is positive when current leaves the object by pin number 3. For more information see ".PLOT" on page 791 and ".PRINT" on page 830.

- . PROBE

The Eldo . probe card is emulated, i.e. all node voltages are dumped in the binary output file (. $w d b$ ). In order to have only those items specified in .PLOT/. PROBE to be dumped in the output file, add . ОРtion probe. For more information see ".PROBE" on page 838.

- . SUBCKT

Usage of global node names in the .subckt definition node list. Eldo will check the node names in the subcircuit list definition prior to the global node list. For more information see ".SUBCKT" on page 898.

- . TEMP

The model parameter tref can be specified. This is equivalent to the parameter tnom when the . temp command is used to apply temperature effects. When tref is specified, тNOM will be ignored.

- . TRAN

If the .TRAN command has four parameters, for example:

```
.TRAN tprint tstop tstart hmax
```

- if value 4 (hmax) < value2 (tstop), it is treated as in Eldo standard mode:
. TRAN tprint tstop tstart hmax
- if value 4 (hmax) $\geq$ value 2 (tstop), it is treated as a list of INCRn Tn values:

```
.TRAN INCR1 T1 [{INCRn Tn}] [TSTART=val] [UIC]
```

For more information see ".TRAN" on page 911.

## Options

- NOINIT

Set for cases where UIC is set on the . TRAN card. For more information, see "UIC" on page 912.

- ACM

This option is automatically set in compat mode. For more information, see "ACM" on page 983.

- ICDC and ICDEv

These options are automatically set in compat mode. This means that IC specifications given on devices are taken into account for the DC which is performed prior to TRAN. When -compat is not set, and neither are the ICDC and ICDEV options, then IC specifications given on devices are ignored, unless the UIC keyword is specified on the .TRAN card. For more information, see "ICDC and ICDEV" on page 978.

- LICN

This option is automatically set in compat mode. Causes the last initial condition (.Ic) specification to have precedence over previous IC specifications.

- (NO) KWSCALE

This option is automatically set in compat mode. Therefore, sCALE is not considered as a keyword and can be used as a parameter. For more information, see " (NO) KWSCALE" on page 991.

- ACOUT=VAL

ACout defaults to 1 .
1
$\mathbf{V} \mathbf{x}(a, b)$ or $\mathbf{I} \mathbf{x}(a, b)$ are computed from the complex value $\mathbf{V} \mathbf{x}(a, 0)-\mathbf{V} \mathbf{x}(b, 0)$ or from
$\mathbf{I x}(a, 0)-\mathbf{I} \mathbf{x}(b, 0)$. For more information, see "ACOUT=VAL" on page 997.

- PROBE
. Probe command is emulated, i.e. all node voltages are dumped in the binary output file (. $w d b$ ). In order to have only those items specified in . PLOt/. Probe to be dumped in the output file, add . OPtion Probe. For more information, see "PROBE" on page 1013.
- Libinc

This option is automatically set in compat mode. It specifies that all the libraries (.LIB) should be included without filtering the objects (model, card or subcircuit) that are not used in the specific netlist. For more information, see "LIBINC" on page 966.

- SLASHCONT

This option is automatically set in compat mode. It allows a single backslash to be used for the continuation of the line. Example:

```
.OPTION SLASHCONT
R1 1 2 \\
3k
R2 1 2 1k
```

R1 will be set to 3 . It is possible to disable this option by using. option nobslashcont.

- PARHIER='local'|'global'

Default is set to global. Global "parent" values have precedence. Example:

```
.SUBCKT R1 1 2
R1 1 2 a
.ends
X1 in out R1 a=2
.param a=3
```

When parhier is local, X1.R1 will be 2, while when parhier is global, X1.R1 is 3 . For more information, see the PARHIER description in the Simulator and Control Options chapter.

- GENK<=val>

This option is automatically set in compat mode. It forces Eldo to generate 2nd order mutual inductors. It is used together with the KLIm option. For more information, see "GENK [=VAL]" on page 986.

- TNOM

тNOM defaults to $25^{\circ} \mathrm{C}$ instead of $27^{\circ} \mathrm{C}$. For more information see "Temperature Handling" on page 88 .

- DEFPTNOM

This option is automatically set in compat mode. Allows a parameter to be defined with the name tNom. In such a case, this value will be used inside parameter expressions, instead of the default $\mathbf{~ т N O M ~ o r ~ t h e ~ v a l u e ~ s e t ~ u s i n g ~ o p t i o n ~} \mathbf{~} \mathbf{N N O M = v a l}$.

- MODWLDOT

This option is automatically set in compat mode. It is used for binned models. For more information, see "MODWLDOT" on page 988.

- noeldoswitch

When specified with the -compat flag/option, it informs Eldo that devices beginning with an $S$ are not switches (Eldo default) but S-parameter block instantiations.

- quotrel

This option is automatically set in compat mode. For more information, see "QUOTREL" on page 959.

- noeldologic

This option is automatically set in compat mode. For more information, see "NOELDOLOGIC" on page 955.

- acderfunc

This option is automatically unset in compat mode. For more information, see "ACDERFUNC" on page 983.

## Options Only Available in compat Mode

The following options are only available in compat mode:

- ALTERELDO

Changes the way the .ALTER re-run feature works in compat mode. In compat mode, for alter index ' n ', Eldo revisits the ' n -1' alter looking for substitution. In default Eldo mode, for alter index ' $n$ ', Eldo only deals with the nominal and the alter ' $n$ '; it ignores the ' $n-1$ ' alter. In other words, in compat mode, alters are cumulative, but not in Eldo default mode. Specify altereldo to activate the default Eldo mode behavior when in compat mode.

## - CKDCPATH

Forces Eldo to issue a warning instead of an error when a dangling node (no DC path to ground) is encountered on a current source. The source is then disabled and the node connected to ground. This option is only used in compat mode.

## - COMPEXUP

Forces Eldo to keep the name of the extraction results (from .EXTRACT and .meas statements) in uppercase. This option is only used in compat mode.

- NOBSLASHCONT

Disables option SLASHCONT which is set by default in compat mode.

## Netlist

## Comment character

Dollar \$ is used as the comment character in the netlist line instead of !.
The comment character is usually considered as such only if the preceding character is a blank space or if the comment is at the beginning of a line. In -compat mode with the comment character \$, then the above rule still applies; additionally, the \$ character is a comment character if:

- the preceding character is not a white space, and
- the first character of the string is ' ', ', ", a number, or a period (.).

If you want to reference an environment variable using the \$ character, for example to specify a file path, surround the path and filename in quotes.

Examples:

- Circumstances where $\$$ is considered as a comment:
- $\$$ is considered a comment because the string begins with the digit 0 :

```
M1... l=0.1u$
```

- \$ is considered a comment because the preceding character is a blank space:

```
M1... l=0.1u $
```

.INCLUDE \$HERE/myfile.txt

- \$ is considered a comment because the first character is a number:

```
M1 1$ d g s b nmos w=1u l=3
```

- Circumstances where $\$$ is not considered as a comment:

```
M1 al$ d g s b...
M2 '1$' d g s b ...
.INCLUDE "$HERE/myfile.txt"
```


## Parameters

Multiple affectation of parameters which can be overwritten sequentially is allowed.
In model instantiations, Eldo will check whether there is a .model with the same name as the string after the nodes in a model declaration. If not, it will look for a parameter name.

In . PARAM statements, LOT and DEv are not considered as keywords, however LOT/GAUSS, DEV/GAUSS, LOT/<distrib_name>, and DEV/<distrib_name> are.

## Quotes

Double quotes are considered as single quotes. (In standard Eldo mode, double quotes are used to specify a parameter string.) Use option quotstr to consider double quotes as a parameter string delimiter.

## Order of analyses

Analyses will be performed in the order specified in the netlist. The order in which analyses will be performed can then differ from the original Eldo order, and there can be multiple analyses of the same type to be run sequentially. In addition, .PRINT/.PLOT/.EXTRACT/.meas commands will be seen only by the preceding command. Example:

```
.tran 1n 10n
.print tran v(1)
.tran 1n 50n
.print tran v(2)
.end
```

With the -compat flag set, the first .tran command will force Eldo to do a transient simulation between 0 and 10 n . Only v(1) will be displayed. The second .tran command will force Eldo to do a transient simulation between 0 and 50 n . Only v(2) will be displayed for that simulation.

## Order of analyses-AC in the middle of a .TRAN

AC in the middle of transient is handled with respect to the compat mode ordering rule (as described above). Whenever a .AC command, a .TRAN command, and a . OP command containing time specifications are specified in the .cir file, then the results will be:

- .ac followed by .tran

AC will be performed during the transient because .ac appears before .tran

- .tran followed by .ac

AC will be performed after the transient, and not inside it. A warning is issued:

```
Warning 1484: AC analysis will not be performed during transient because
of the commands ordering.
```

- .tran followed by .ac followed by another .tran

The first transient is performed, then AC + transient as in the first case

## Arithmetic Functions and Operators

When the -compat flag is active, the following arithmetic function/operator rules apply:

```
log(x) = sign(x) * log(abs(x))
log10(x) = sign(x) * log10(abs(x))
db}(x)=sign(x) * 20.0*log10*abs(x)
```

sqrt (x) is -sqrt (abs(x)) if $x$ is negative.
$x^{* *} *_{n}$ is computed as $x *_{n}$ if $x$ is positive, $-\left(\operatorname{abs}(x) * *_{n}\right)$ if $x$ is negative, and 0 if $x$ is 0 .
The power operator $\left(^{\wedge}\right)$ has highest precedence (same as standard Eldo); prior to v6.3_2 it had lower precedence in -compat mode than the multiplication and division operators.

## Note

In Eldo standard mode:
sqrt ( $x$ ) returns an error if $x$ is negative.
$\mathrm{x}^{* *} \mathrm{n}$ is computed as $\exp (\mathrm{n} * \log (\mathrm{x}))$ if x is strictly positive, 0 otherwise.

Tip: For more information, see "Arithmetic Functions" on page 78.

## EVAL keyword

When the -compat flag is active, the function keyword EVAL is not required in conditional expressions. For example:

```
r1 1 2 '(p1 > p2 ? p2: p1)'
```

Will be the equivalent of:

```
r1 1 2 'eval(p1 > p2 ? p2: p1)'
```


## Output Format

The following types of output files are generated when the -compat flag is active:

- If option $\operatorname{pOSt}=1$ or $\operatorname{pOSt}=2$, Eldo generates only.$t r 0$ output files, no.$w d b$ file generated.
- Without specifying option post, Eldo generates only .wdb output files.


## TIspice Compatibility

Eldo provides partial compatibility with TIspice version 3.40. TIspice is developed by Texas Instruments Incorporated. This section describes some specific TIspice syntax that is compatible inside Eldo.

Eldo TIspice compatibility is invoked as follows:

```
eldo -tispice ... cir_file_name
```

or by adding in the netlist the following option:
.OPTION TISPICE
This section shows the different effects that this compatibility mode has.

## Devices

## Model mapping

The following Eldo Levels are set:
Table 25-5. MOS Levels in TIspice Compatibility Mode

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
| 4 | Berkeley BSIM1 (Eldo LEVEL 8) |
| 8 or 49 | Berkeley BSIM3 v3.0 \& BSIM3 v3.1 (Eldo LEVEL 53) |
| 9 | Berkeley BSIMSOI3v3.1.1 PD (Eldo LEVEL 56, SOIMOD=0) |
| 14 or 54 | Berkeley BSIM4.0.0 (Eldo LEVEL 60) |

Table 25-6. BJT Models in TIspice Compatibility Mode

| LEVEL | Model Name (Eldo Level) |
| :--- | :--- |
|  | VBIC v1.2 (Eldo LEVEL 8) |
|  | (VERSION=1.15) VBIC v1.1.5 (Eldo LEVEL 8) |
| 504 | Philips Mextram 504 Model (Eldo LEVEL 22) |

## Resistor and capacitor model syntax

.MODEL R or C: SCALE equivalent to Eldo R or C
.MODEL R and no level => level = 5
.MODEL C and no level => level = 5

## Resistor model level 5

This is the default resistor model when in Eldo TIspice compatibility mode. L and W are instance parameters. Model parameters:

RSH Sheet resistivity. Unit is Ohm/square. This value is mandatory.
LR The reduction in length from side etching. NARROW overrides this parameter. Default is 0 .

NARROW The narrowing of the resistor due to side etching. The units for this are meters, and the default value is 0 .

WR The reduction in width from side etching. NARROW overrides this parameter. Default is 0 .

SCALE The scaling factor (on top of all other calculations) used to multiply the value of the resistance before analysis. The default value is 1 .

The R value is computed as:

$$
\mathrm{R}=\mathrm{RSH} \times(\mathrm{L}-\mathrm{LR}) /(\mathrm{W}-\mathrm{WR})
$$

If neither $L$ or $W$ are specified, then it is assumed that the $R$ value is specified on the instance card: then only model parameter SCALE will be considered.

## Capacitor model level 5

This is the default capacitor model when in Eldo TIspice compatibility mode. Model parameters:
cj The junction bottom capacitance for semiconductor capacitors. Units for this are farads/square meter. This parameter must be specified for a semiconductor capacitor.
cjsw The sidewall junction capacitance in farads/square meter for a semiconductor capacitor. This is also a required model parameter for a semiconductor capacitor.
defw The default width for a semiconductor capacitor. A W=width statement on capacitors overrides this value. The units for this are meters, and the default value is $1 \mathrm{E}-6$.
narrow The narrowing of the capacitor due to side etching in the case of semiconductor capacitors. The units for this parameter are meters, and the default value is 0 .
scale $\quad$ The scaling factor (on top of all other calculations) used to multiply the value of the capacitance before analysis. The default value is 1 .

Usage of these model parameters depends on how the device has been instantiated:

- if W or L specified:
$\mathrm{C}=\mathrm{CJ} \times(\mathrm{L}-\mathrm{NARROW}) \times(\mathrm{W}-\mathrm{NARROW})+2 \times \mathrm{CJSW} \times(\mathrm{L}+\mathrm{W}-2 \times$ NARROW $)$
- if AREA or PERI specified:
$\mathrm{C}=\mathrm{CJ} \times\left(\right.$ AREA - NARROW $\times$ PERIMETER $/ 2+$ NARROW $\left.^{2}\right)+\mathrm{CJSW} \times$ (PERIMETER $-4 \times$ NARROW)
- None specified: C is assumed to be specified on the instance card.


## Resistor, self inductor and capacitor

The model name, if any, is placed after the nominal value for a non-geometric model, and before any parameter for a geometric model:

```
R1 a b value MODEL TC1 = 1
R1 a b MODEL L = ...
```

In the case of a non-geometric model, the 5th token can be a special parameter name rather than a model name. If the 1st letter of the 5th argument is a P, then Eldo will look for a parameter rather than a model. The value of that parameter is a multiplier of the device. For example:

```
R1 1 2 1k pr
.param pr = 2
```

The actual value of R 1 will be 2 k .

## MOS length and width

Length and width of MOS are supposed to be given in Microns. Same for PD and PS. AD and AS are also expected in Microns ${ }^{2}$. The default in Eldo is meters.

## Commands

## .PARAM command

The ' $=$ ' is not mandatory on the .PARAM but if the ' $=$ ' is omitted, there can be only one parameter defined per . PARAM statement.

## .LIB command

If dns=/path on a . LIB statement is specified, the dns= is ignored. This was old TIspice syntax.

## .TRAN command extension

The full TIspice . TRAN syntax is accepted.

TMIN sets hmin
TSHIFT sets time at which all independence sources begins their evaluation
TPUNCH creates a save file for each tpunch timepoint
WRINIT RDINIT RDFORCE WRFINAL
handles init filenames
The following options are accepted but ignored: SAVE, CHECKSTOPDELAY, TRNOISE, INITERROR.

## .INCLUDE/.LIB commands

These commands accept the syntax SECTION = <>, which gives the corner name of the library.
When noprint is specified the library netlist is not dumped in the output (.chi) file.

## .RERUN command

Same as the Eldo .ALTER command except that a .END statement is required between each . RERUN.

## .PRINT/.PLOT command extensions

General form:

```
.print analyse_type signal_list
.plot analyse_type signal list
```

signal_list is the collection of output variables. TIspice output variables can be specified in one of five ways:

- using a full name format
- using a partial name format
- using regular expression format
- specifying depth of hierarchy
- using a mathematical-expression format

Currently only partial name and full name formats are supported in Eldo. An example of partial name format is:

```
.print ac all(v i) except(i(x1.x1)
```

This prints all node voltages and all currents except any current in the subcircuit x1.x1.
Output variables supported by Eldo are:

- Voltage at nodes, for example:

```
v(4) v(5,3) v(2 4,5 out x1.1)
```

- Voltage on devices, for example:

```
E(Q1,BE,CE M1,DS)
E(C1,PN) E(C2)
```

Note: reversing voltage is not supported yet in Eldo. i.e. $\mathrm{E}(\mathrm{Q} 1, \mathrm{~EB})$ and $\mathrm{E}(\mathrm{C} 1, \mathrm{NP})$ will both be ignored.

Note: default keyword handling is fully supported by Eldo. $\mathrm{E}(\mathrm{C} 1)$ is similar to
$\mathrm{E}(\mathrm{C} 1, \mathrm{PN})$. But the voltage may not exist in Eldo, so $\mathrm{E}(\mathrm{M} 1)$ will be ignored in Eldo as it is similar to $\mathrm{E}(\mathrm{M} 1, \mathrm{DG})$.

The supported keywords are:
Table 25-7. Supported Keywords for Voltage on a Device

| Element type | Supported keywords |
| :--- | :--- |
| JFET | DS, GS |
| MOSFET | DS, GS, GB, BD, BS |
| BJT | CE, BE, BC |

- Current in a device terminal, for example:

```
I (Q1,C,B,E D J1,D,G,S M1,D,G,S,B XA.Q1,B,C)
```

Note: default keyword handling is fully supported by Eldo.

- Current density in a device

Not supported for resistors, diodes, JFETS, MOS and BJTS, otherwise its is equivalent to current.

- Power, for example:

P(Q1 Q2)
Note: Time averaging is not currently supported. $\mathrm{P}(\mathrm{Q} 1, \mathrm{TA})$ will be ignored.

- Noise variables, for example:

```
INOISE ONOISE(DB) ONOISE
```

When in TIspice compatibility mode the output variable names are assumed to be in the TIspice format. To keep the Eldo format with TIspice compatibility mode you must use the option tieldoof.

So in TIspice compatibility mode and with option tieldoof specified, the following statement will give an error:

```
.print dc E(D1,PN R1)
```


## .PUNCH command

The TIspice . Punch command is synonymous with the Eldo .Probe command.

## .FOUR command extension

This calculates the fourier coefficients for the sinusoidal harmonic components of any output variable in the circuit. This command creates a table containing:

- DC component
- FOUR_NCOEFF first Fourier coefficients
- Total harmonic distortion THD


## .FORCE command

Forces one or more nodes to specified voltage(s) with respect to ground for the initial transient solution. This is similar to the Eldo .IC command, values will be used only for the DC performed prior to TRAN analysis. Both commands are used to give values replacing the DC solution. With the .FORCE syntax, initial values of inductors current can be given while with Eldo . Ic only node voltages can be initialized including nodes inside subcircuits. Syntax:

```
.FORCE [NODE] node_name1 value1... node_name2 value2...
+ [IND|OBJECT] object_name1 value1...
```

node_name Node name.
VALUE Value at node.
IND|OBJ Inductor or object. For objects, only voltage source components can be specified to set the current on.
object_name Inductor or voltage source component.

## .INITIAL command

Specifies estimated solutions of DC analyses to improve DC convergence. This is similar to the Eldo .NODESET command, but analysis type can be specified, and . INITIAL can also be applied to impose .nodeset conditions on devices. Syntax:

```
.INITIAL ANALYSIS [NODE] node_name1 value1... node_name2 value2...
+ [IND|OBJECT] object_name1 value1...
```

ANALYSIS Type of analysis can be OP, TR or DC[SWEEP].

OP
Initial conditions for operating point analysis.
TR
Initial conditions for transient analysis.
DC
Initial conditions for DC analysis.
node_name Node name.
VALUE Value at node.
IND|OBJ Inductor or object. For objects, only voltage source components can be specified to set the current on.
object_name Inductor or voltage source component.
Examples:

```
.INITIAL OP A 5V
.INITIAL TRANSIENT A 4V
```

When an OP analysis is being performed, 5 V will be used as a NODESET value. When a TRAN analysis is being performed, 4 V will be used as a NODESET value

```
.INITIAL DC IND L1 5m
```

During a DCSWEEP analysis, a value of 5m will be used as NODESET value for the current flowing through object L1.

## .ECHO command

Echo on/off is used to switch on/off the netlist lines to write to the output (.chi) file. The netlist lines between the echo off/on statements are disabled.

```
.ECHO ON|OFF [<string>]
```

The optional string on the echo command is always dumped.
Example:

```
*test ti
.param n=1
.param k=0
.param k1=n**k
.echo off "END OF DUMP"
v1 1 0 #n**k#
R1 1 0 1k
.echo on "RESTART THE DUMP"
.op
.print op v(1)
.end
```

The part of the netlist between echo off and echo on will not be written in the output file because echo has been disabled (.echo off). The last part will be written because echo has been reenabled (.echo on).

## Netlist

## Model selection using parameter string

```
X1 ... MOD = foo
M1... %MOD% ... -> model foo will be used
```


## Value "x"

x indicates unit 1e6 i.e. 2 x represents 2.0e6. MEG is required in Eldo.

## Expressions

Mathematical expressions can be enclosed in pound signs (\#) or single-quotes (').

## Parameter statements

Two ways of writing TIspice parameter statement allowed:

P pname [=] value [TC=<TC1> [, <TC2>]]
or:
. PARAM pname value [TC=<TC1> [, <TC2>]]
PR, PL, and PC are pre-defined parameter names that act as scaling factors for all resistors, inductors, and capacitors respectively in the circuit. These default to 1 and can be changed using this statement. These can be defined local to subcircuits and also passed as subcircuit parameters. Use extreme caution in using these parameter names, as they change the values of all R , L , and C elements in the circuit.

## Functions and Sources

## Delay

DELAY is equivalent to TD or SHIFT in PWL signals.

## Sources

Current and voltage sources SIN, SFFM, AM, EXP allowed.

## Dangling Nets Options

ALLOW_DANGLING_NETS causes Eldo to find all nets in the circuit with only one connection and connect each one to ground through a resistance of 1/GMIN.

NOALLOW_DANGLING_NETS causes Eldo to give a topology error and stop if any nets are found with only one connection.

## Eldo Extensions for Tlspice Compatibility

## .DC command extensions

- Sweep of gain for linear controlled sources

The .DC command has been extended to support the sweep of gain for linear controlled sources VCVS, CCVS, CCCS, VCCS. Only the linear case is supported and only the gain of these sources may be swept. Example:

```
.dc E1 3 5 0.5
```

The gain of the VCVS E1 will be swept from 3 to 5 in increments of 0.5 .
See ".DC" on page 588.

- Third level dc sweep

The DC sweep can be nested up to three levels deep. Example:

```
.dc v1 2 3 0.5 v2 5 9 0.5 v3 -1 2 0.1
```


## .DEFAULT command

This command resets the default values for elements, device initial conditions and model parameters.

The general form for resistors, capacitors, and inductors is:

```
.DE[FAULT] TYPE VALUE
```

The general form for other types is:

```
.DE[FAULT] TYPE {KEYWORD [VALUE]}
```

Eldo implementation of . Default does not support the Lossy Transmission Line (LDTL) model and IC for active devices are ignored.

See ".DEFAULT" on page 600.

## .MEAS command extension

For the trigger and target specification formats of the .meas command, SIG_H and SIG_L are also available. These represent the High and Low signal values respectively. Default high and low values are trig_val for the trigger signal and targ_val for the target signal. These high and low values are used to validate a transition before incrementing the cross, rise or fall counter.

These specifications are allowed in both standard Eldo mode and TIspice mode.
See ".MEAS" on page 717.

## .MSELECT command

Automatic model selection. This command allows you to select model automatically for MOS devices. The selection is based on:

- the size and temperature of the specific device (W, L, TEMP)
- the size and temperature constraints of each model in the list provided (WMIN, WMAX, LMIN, LMAX, TEMPMIN, TEMPMAX)

Syntax:

```
.MSEL[LECT] dummy [models] mod1 [mod2 [mod3 [...]]]
```

It is not allowed to have a model statement with the same name as an mselect dummy model name.

## .SCALE command

This command scales device and model parameters of active devices automatically.
The general form for devices (elements) is:

```
.SC[ALE] ELTYPE KEYWORD VALUE [KEYWORD VALUE ...]
+ [ELEMENTS ALL|EXCEPT] [ELNAME1 ELNAME2 ...] [(ELNAME1 ELNAME2)]]
.SC[ALE] ELTYPE KEYWORD VALUE [KEYWORD VALUE ...]
+ MODELS MODNAME1 [MODNAME2 ...]
```

The general form for devices models (models) is:

```
.SC[ALE] MODTYPE KEYWORD VALUE [KEYWORD VALUE ....]
+ [MODELS ALL|EXCEPT] [MODNAME1 MODNAME2] [(MODNAME1 MODNAME2...)]]
```

An additional feature is parameter scaling:

```
.SC[ALE] P FACTOR=VALUE [SUBCKT=SUBNAME] [INST=INSTNAME]
+ [PARAMS ALL|EXCEPT] [PARAM1 PARAM2 ...] [(PARAM11 PARAM22)]]
```

The element parameters or devices are only scaled at the parsing level.

If a .DC is used on a device element with a scale factor, the device element takes only the value specified by the DC analysis. There is no scaling effect.

The naming convention of devices, parameters, and models follows the Eldo naming convention if the tispice option is not set. The TIspice naming convention is followed if the option is set. TIspice uses partial names instead of wildcards, i.e. MOD1 means all names beginning with MOD1: MOD12, MOD1TT, MOD1, MOD1_A11, for example. In Eldo mode wildcards must be specified: MOD1*.

## EBIT and PBIT source functions

The TIspice EBIT and PBIT source functions have been implemented. These represent exponential pulse with bit pattern and trapezoidal pulse with bit pattern sources respectively.

The full TIspice specifications are used in TIspice mode. However, standard Eldo also has access to this command, with the following changes:

- the TIspice optional parameter TD is specified as a mandatory first argument in Eldo
- the TIspice optional parameter NONPERIODIC is replaced in Eldo by the R keyword which can be found also on the original PATTERN Eldo statement
- the $\$$ sign which must be set before the pattern string in TIspice is not required in Eldo
- Eldo does not allow specifying a file containing the bit pattern

For example, in TIspice, the statement:

```
v1 1 0 ebit 1 5 1n 0.5n 0n 1n 5n $101011101000011
```

is written in Eldo standard mode as:
v1 10 ebit $150 n 1 n 0.5 n 0 n 1 n 5 n 101011101000011 R$
See "Exponential Pulse With Bit Pattern Function" on page 348.

## Spectre Compatibility

Eldo can use a Spectre netlist as input. There are two flows to simulate a Spectre netlist in Eldo:

- Spectre compatibility flow

Run Eldo on the Spectre netlist. Eldo will call the spect2el script to convert netlists from Spectre format (Spectre language syntax) into Eldo format (Eldo syntax). Additionally, spect2el generates several files that will be used to map the Spectre name to a SPICE name, and to avoid the reconversion of the Spectre files if nothing has changed in them. This flow is more straightforward and more efficient. This is the preferred approach.

- Spectre to Eldo Converter flow

This flow is based on the spect $2 e l$ script that converts libraries and netlists from Spectre format (Spectre language syntax) into Eldo format (Eldo syntax). You then run Eldo on the converted netlist. This flow offers more flexibility, in particular if manual modifications are necessary to workaround unexpected conversion issues. See Spectre to Eldo Converter for more information on the spect2el script.

## Usage

The Spectre netlist can be specified on the Eldo command line with the following syntax:

```
eldo -sp spectre_file [-s2emode 2|1] [-i spice_command_file]
[-clean_sp] [-spectre_out pathname] [-sp_plot 2| 1|0]
```

- -sp spectre_file

The filename of the Spectre format netlist to be used as input for Eldo. spectre_file must be specified with an extension. No guess is made on the possible extension. If the filename is specified without its extension it will lead to an error.

- -i spice_command_file

The filename of the Eldo/SPICE command file to be used in association with the Spectre netlist. Optional. Used with the -sp argument when a Spectre netlist is the input.
spice_command_file must be specified with an extension. No guess is made on the possible extension. If the filename is specified without its extension an error will be generated. The spice_command_file must not include the spectre_file. Eldo will automatically perform the link between these files. Including the Spectre file will not work and the simulation will stop.

- -s2emode 2|1

Used to switch between the old (pre-2009.1) and new converter. Optional. Used with the -sp argument when a Spectre netlist is the input. Set to 1 to run the old converter. Set to 2 (default) to run the newer one, which provides speed and robustness advantages. If errors occur when -s2emode 2 is specified, a file named spect2el.error will be generated clearly describing the errors.

- -clean_sp

Removes all the files generated by spect $2 e l$. As a consequence, if you want to relaunch the simulation on that design, the converter will reproduce the work. This will increase the overall simulation time. Optional. Used with the -sp argument when a Spectre netlist is the input.

- -spectre_out pathname

Define the path in which the files generated by spect2el reside. Optional. Used with the -sp argument when a Spectre netlist is the input. Eldo creates pathname automatically if it does not exist. If -clean_sp is also specified, Eldo clears the files/subdirectories under pathname, while pathname itself is not removed after simulation. By default, pathname is identical to the one specified by -outpath.

- -sp_plot 2|1|0

Controls the conversion of Spectre save statements into Eldo .PRINT, .PLOT and . probe commands as below:
if -plot 0 , the converter will convert the save statement into .PRINT (default).
if -plot 1 , the converter will convert the save statement into .-Рцот.
if -plot 2, the converter will convert the save statement into .probe.

## Note

Eldo launches spect $2 e l$ with the following options:
-do_va 1 -netlist_converter 1
You cannot change these options when running from the Eldo command line.

## Description

spectre_file and spice_command_file must be specified with their extensions. No attempt is made by Eldo to surmise the possible extension. If the filename is specified without its extension an error will be generated. See Table 25-9 for example error messages.

The convention for the generated files is as follows:

- the converted SPICE files are written to the folder named [outpath].spectre_file_dir/
- the files generated for name mapping purpose are written to the folder named [outpath].spectre_file_map_dir/
- the files generated to avoid the (re)conversion of the Spectre files, when it is not necessary, are written to the folder named [outpath].spectre_file_db_dir/
You can manually remove these folders if they are no longer required. An alternative output directory can be specified with the -spectre_out pathname flag.

The spice_command_file must not include the spectre_file. Eldo automatically performs the link between these files. Attempting to include the Spectre file will not function, and the simulation will stop. See Troubleshooting Include Files for examples.

All SPICE commands (.рLOt/. Probe/.step/.extract, and so on) can be used except for the .ALTER command, where the mapping is not handled. When specifying a name for the .PLOT command, the Spectre names can be used.

## Note

Be aware that every device name or node name is case insensitive because SPICE language is being used. This differs from Spectre which is case sensitive.

For example, if the Spectre design contains:

```
aRes n1 n2 resistor r=1k
ares n1 n2 resistor r=2k
```

Eldo (SPICE) is case insensitive, so it will consider resistor "ares" has been defined twice. Spectre is case sensitive so differentiates between "aRes" and "ares."

Here follows a simple example:

```
spectre_file.sp:
    simulator lang=spectre
    subckt foo a b
    Aresfoo a b resistor r=1k
    ends
    subckt bar a b
    Aresbar a b resistor r=1k
    myInstance a b foo
    ends
    anotherInstance 1 0 bar
```

spice_command_file.cir:
*first line
c1 $101 p$
$\begin{array}{llll}\text { I1 } & 1 & 1\end{array}$
.plot tran I(anotherInstance.*)

- plot tran v(c1)
.tran 1n 10n
. end

Eldo can be launched on the Spectre design by entering the following:

```
eldo -sp spectre_file.sp -i spice_command_file.cir
```

In the.$w d b$ output file, the name of the plotted elements are as defined in the Spectre design. In this example, I(ANOTHERINSTANCE.ARESBAR) will be plotted.

## Spectre Default Constants and Functions

When using Eldo with the command line flag -sp, or if option use_spectre_constant is specified in the SPICE netlist, Eldo understands a number of Spectre default parameters, constants, and functions as follows:

- Spectre instance parameter trise is handled as an alias to dtemp for all instances
- Spectre instance parameter perim is handled as an alias to peri for diode instances
- Spectre default constants and functions as listed in Table 25-8 are allowed:

Table 25-8. Spectre Constants and Functions

| Constant/Function | Value |
| :--- | :--- |
| m_e | 2.7182818284590452354 |
| m_log2e | 1.4426950408889634074 |
| m_log10e | 0.43429448190325182765 |
| m_ln2 | 0.69314718055994530942 |
| m_ln10 | 2.30258509299404568402 |
| m_pi | 3.14159265358979323846 |
| m_two_pi | 6.28318530717958647652 |
| m_pi_2 | 1.57079632679489661923 |
| m_pi_4 | 0.78539816339744830962 |
| m_1_pi | 0.31830988618379067154 |
| m_2_pi | 0.63661977236758134308 |
| m_2_sqrtpi | 1.12837916709551257390 |
| m_sqrt2 | 1.41421356237309504880 |
| m_sqrt1_2 | 0.70710678118654752440 |
| m_degperrad | 57.2957795130823208772 |
| p_q | $1.6021918 \times 10^{-19}$ |
| p_c | $2.997924562 \times 10^{8}$ |
| p_k | $1.3806226 \times 10^{-23}$ |
| p_h | $6.6260755 \times 10^{-34}$ |
| p_eps0 | $8.85418792394420013968 \times 10^{-12}$ |
|  |  |

Table 25-8. Spectre Constants and Functions

| Constant/Function | Value |
| :--- | :--- |
| p_u0 | $\mathrm{m} \_\mathrm{p} i \times 4.0 \times 10^{-7}$ |
| p_celsius0 | 273.15 |
| f_mod(a,b) | $\{\mathrm{a}-\mathrm{b} \times \operatorname{int}((\mathrm{a}+0.5) / \mathrm{b})\}$ |
| $\operatorname{atan} 2(\mathrm{a}, \mathrm{b})$ | $\{\operatorname{atan}(\mathrm{a} / \mathrm{b})\}$ |
| hypot $(\mathrm{a}, \mathrm{b})$ | $\{\operatorname{sqrt}(\mathrm{a} \times \mathrm{a}+\mathrm{b} \times \mathrm{b})\}$ |

These constants can be used inside all expressions.

## Limitations

- The .alter command is not supported.
- When Eldo is using a Spectre netlist as input, and the netlist contains an internal node and a device with the same name, it is impossible for Eldo to distinguish between these. When Eldo analyses a subcircuit in the Spectre netlist, each element is attempted to be converted, without knowing if it is a node name or a device name. This can lead to plots not being performed as expected, because Eldo will not know what kind of plot is required (I or V for example). See Troubleshooting Spectre Node and Device Names for examples.


## Troubleshooting

## Include Files

The spice_command_file must not include the spectre_file, and vice versa. Eldo automatically performs the link between these files. Attempting to include the Spectre file will not function, and the simulation will stop.

- the SPICE file includes the Spectre file

Eldo will not be able to parse the Spectre file, leading to the following syntax error message (example):

```
ERROR 208: In file "./t1.sp" line 5:
+ OBJECT "AOP": Unrecognized character or word A
```

In this example, Eldo considers that "Aresfoo" in line 5 is requesting an aop (opamp).

- the Spectre file includes the SPICE file

If you have the following top Spectre file, where tl.cir should be the spice_command_file:
simulator lang=spectre

```
subckt foo a b
    Aresfoo a b resistor r=2k
ends
subckt bar a b
    Aresbar a b resistor r=1k
    myInstance a b foo
ends
anotherInstance 1 0 bar
simulator lang=spice
.include "t1.cir"
```

The Spectre to Eldo converter will not understand the . Include statement and so will not change its path nor copy the t1.cir file into the .tl.sp_dir folder. Eldo might find it, and proceed with the include, however it could also fail to find it and raise an error message.

Moreover if the file is both included and specified using the -i command line option, you will have duplicate definitions, as the file is effectively included twice.

Spectre does not understand SPICE syntax, which means only a full Spectre design can be used. However spectre_file could contain subcircuit definitions and Spectre library inclusion, and have its full design in the spice_command_file which may include some SPICE libraries.

To summarize, from one side a full Spectre tree is allowed and from the other a full SPICE tree. That can be a way to specify complex design mixing both SPICE and Spectre.

## Spectre Node and Device Names

When Eldo is using a Spectre netlist as input, and the netlist contains an internal node and a device with the same name, it is impossible for Eldo to distinguish between these. When Eldo analyses a subcircuit in the Spectre netlist, each element is attempted to be converted, without knowing if it is a node name or a device name. This can lead to plots not being performed as expected, because Eldo will not know what kind of plot is required (I or V for example).

If topsp, the Spectre input file, contains a subcircuit instance named $x 1$, and the SPICE command file, cmd.cir, contains:
.plot dc v(x1.c1)
then c 1 must be an internal node name as a voltage plot is requested.
However, if cmd.cir contains:

```
.plot dc I(x1.c1)
```

then c 1 must be a device name as a current plot is requested.
When Eldo is using a Spectre netlist as input, Eldo does not initially know the kind of plot requested (I or V). Therefore, when Eldo analyses $x 1 . c 1$, each element is attempted to be converted; $x 1 . c 1$ will be mapped to $x x 1 . y y$, where $y y$ can be $c c l$ if there was a capacitor named $c l$ in that subcircuit in the Spectre design, or $c 1$ if there was no capacitor named $c l$.

So if the following is specified:
.plot dc v(x1.c1)
it will be equivalent to .plot $\mathrm{dc} \mathrm{v}(\mathrm{xx} 1 . \mathrm{cc} 1)$ if c 1 is defined as a device, no matter if it is a node name or not. In this case, the plot will not be performed.

## Error Messages

Table 25-9. Spectre Conversion Error Messages

| Error Code | Message | Description |
| :--- | :--- | :--- |
| 5 | Unable to open the temporary file <br> "a_name". | Eldo cannot create a temporary file <br> required to process the simulation. The file <br> contains the converted Spectre design and <br> the SPICE command file, if there is one. |
| 33 | Spectre file not specified. | Option -sp has been specified without a <br> filename (eldo -sp). |
| 1602 | outpath not specified. | Option -outpath has been specified without <br> a filename (eldo -sp topsp.sp -outpath). |
| 1603 | Spectre input file is a directory. <br> exist. | The specified Spectre file is in fact a <br> directory name. |
| 1604 | Error: Unable to create the <br> directory "a_name". Either you <br> don’t have write access or there is <br> not enough space left on device. | spect2el cannot create the directory that <br> will contain the converted design. |
| 1605 | preprocessing of the Spectre files <br> failed. | spect2el did not convert the Spectre design <br> properly. Some missed cases may remain <br> (when using the alterblock in Spectre for <br> example). <br> As above but with file and path <br> specified or if the file doestension was not <br> information displayed. |
|  | Flease refer to <path>/spect2el.log the specified Spectre file. <br> file for more details. |  |

Table 25-9. Spectre Conversion Error Messages

| Error Code | Message | Description |
| :--- | :--- | :--- |
| 1606 | preprocessing of the Spectre files <br> failed. <br> Please refer to spect2el.log file for <br> more details. | As above but when the Eldo -outpath <br> argument is not specified. |

## Spectre to Eldo Converter

The Spectre to Eldo converter is a tool script that converts libraries and netlists from Spectre format (Spectre language syntax) into Eldo format (Eldo syntax). The script is named spect2el. See "Usage" on page 1407.

## Prerequisites

- Korn shell must be installed under the /bin directory. The tool will not be able to run if /bin/ksh cannot be invoked.
- The "gawk" utility. This is provided along with the tool.


## Supported Features

The tool can convert Spectre syntax to guarantee compatible results for:

- Basic component instantiations
- Device models and instances
- Subcircuit definitions and instances
- nport instances
- Controlled sources
- Functions and "if" statements
- Statistics
- Conversion of some of the device models written with SPICE syntax (simulator lang=SPICE). These models are: MOSFET models (nmos and pmos) MOS1, MOS2, MOS3, BSIM1, BSIM2, BSIM3, BSIM3v3, and BSIM4 (Spectre levels 1, 2, 3, 4, 5, 10, 11, and 54 respectively); BJT model (npn, pnp, lnpn, and lpnp), Spectre BJT (equivalent to Eldo level 1 as Spectre does not support level for BJT); Diode model (Spectre levels 1 and 3).

The tool can handle libraries with nested includes for any number of levels and for any directory structure.

The following Spectre device models are supported:

- BSIM3v3 MOS model
- Philips PSP 102 MOS model

The following models are supported: psp1010, psp1020, pspnqs1020, psp1011, psp1021, pspnqs1021, psp101, psp102e, and pspnqs102e

- Philips MOS Model 11 Level 1102

The following models are supported by the converter as Eldo Level 69: mos 11021, mos11021t, mos11020, mos11020t, mos1102e, and mos1102et

- Philips MOS Model 11 Level 11010
- VBIC bipolar model
- HICUM bipolar model
- BJT level one model (Gummel Poon)
- Diode level one model
- JFET level one model
- MOS1 model
- Polynomial models for R, L, and C
- Geometric Resistor model
- Physical Resistor model (phyres)
- MOS0 model. (However, since this model has no equivalent in Eldo, it is mapped to the MOS level=1 model of Eldo. Full compatibility is not guaranteed.)
- Bsource instances (r, l, c, i, v, q, g, and phi sources).


## Notes

- Other device models are converted from the syntax point of view only with primary compatibility testing. The list includes: BSIM4, DP500, MOS2, MOS3, BSIM1, BSIM2, BSIM3v2, EKV, BSIMSOI3 PD, GAAS, TOM2, BJT504, BJT504t, JFET level 2, JFET level 4, PSP, TFT Polysilicon, TFT Amorphous, Mextram504, HICUM Level0, MOS2002, JUNCAP, JUNCAP2, JUNCAP_ELDO.
- For proper conversion of netlists or libraries, all the included files should exist. If any instance in the input library or netlist refers to a model, a subcircuit, or a Verilog-A module, which is not defined in the input library/netlist or one of its included files, this instance cannot be recognized or converted and a warning message will be displayed in the running terminal. The conversion will continue if running the tool in standalone mode. However, if running the tool from inside Eldo, the converter will exit with error
code 10 informing that this line is not converted and the conversion process will not continue until this error is corrected. In the new converter, -s2emode 2 , a file named spect2el.error will be generated clearly describing the errors.


## Netlist Conversion

The netlist conversion features come with the spect 2 el tool. This feature automates the netlists conversion process from Spectre syntax to Eldo syntax. The following features are supported:

## Analyses

- AC analysis
- DC analysis
- Transient analysis
- S parameters analysis
- Monte Carlo analysis
- Sweep analysis
- Noise analysis
- Sensitivity analysis
- Transfer function analysis
- Stability analysis


## Note

The above analyses types are partially supported. There are some combinations that are not yet supported.

## Control statements

- Option statements:

| Reltol | Vabstol | Iabstol | Temp |
| :--- | :--- | :--- | :--- |
| Tnom | Scalem | Scale | Gmin |
| Digits | Pivrel | Pivab |  |

- Paramset statement
- Save statement
- Assert statement

With the assert statement, you can set custom characterization checks to specify the safe operating conditions for your circuit. The Spectre circuit simulator then issues messages telling you when parameters move outside the safe operating area and, conversely, when the parameters return to the safe area.

The conversion of assert statements that use parameters inside expressions like below is not yet supported:

```
check assert expr=p2/p1 min=2 max=3
```

Using model types as a primitive with the assert statement like below is not yet supported:

```
check assert primitive=bsim3v3 param=l min=10u max=100u
```

- Simple combinations of alter and set statements


## Sources

- Independent Sources:
- Isource
- Vsource
- Controlled Sources:
- VCVS
- VCCS
- CCVS
- CCCS
- Polynomial Controlled Sources:
- Pcccs
- Pccvs
- Pvecs
- Pvevs


## Components

- Primitive components (resistor, capacitor, diode, inductor, mutual inductor)
- MOSFET, JFET, Bipolar transistors
- Relay

The four-terminal relay is a voltage controlled relay tied between terminals t 1 and t 2 . The voltage between terminals $p s$ and $n s$ controls the relay resistance. The relay resistance varies nonlinearly between ropen and rclosed, the open relay resistance and closed relay resistance, respectively. These resistance values correspond to control voltages of $v t 1$ and $v t 2$ respectively.

- Ideal switch

Single-pole multiple-throw switch with infinite off resistance and zero on resistance. The switch is provided to allow you to reconfigure your circuit between analyses.

When the switch is set to position 0 , it is open. In other words, no terminal is connected to any other. When the switch is set to position 1 , terminal 1 is connected to terminal 0 , and all others are unconnected. When the position is set to position 2, terminal 2 is connected to terminal 0 , and so on.

The switch can change its position based on which analysis type is being performed using the $\mathrm{xxx} \_$position parameters.

- Transformer
- Delay Line

The delay line model is a four-terminal device with zero output impedance and infinite input impedance. The output between nodes $p$ and $n$ is the input voltage between nodes $p s$ and $n s$, delayed by the time delay $t d$ and scaled by gain.

- A2D

The analog-to-logic converter transfers analog waveforms to a logic simulator.

- D2A

The logic-to-analog converter converts a binary signal from a logic simulator to an analog waveform.

- Verilog-A instances
- Current probe (iprobe)
- Independent resistive source (port)


## Limitations

- The following features cannot be converted with the tool. They require some manual modifications.
- Libraries and netlists must be case insensitive. Case sensitive libraries and netlists cannot be handled.
- Libraries and netlists must use Spectre's syntax (simulator lang=spectre). Any SPICE syntax should be preceded by "simulator lang=spice" to be correctly
handled. To include Eldo library files, precede the syntax by "simulator lang=eldo" to be correctly handled.
- Nested sweeps that sweeps more than one paramset. For example:

```
sweep1 sweep paramset=paramset1 {
    sweep2 sweep paramset=paramset2 {
    }
    }
```

- Complicated combinations of the alter set statements.
- Statistical data defined in a separate file with the standard deviation set to a parameter value with this parameter defined in the same separate file will cause simulation errors when the parameter affected by this statistical data is in another file. The problem can be avoided by including this separate file in the netlist after conversion. This limitation is not existing now when using the new converter,
-s2emode 2.
- In the PWL definition, a maximum of 500,000 pairs are accepted. If this number is exceeded, the conversion will fail.
- Long lines, it is advisable that any line should not be longer than 2,000 characters, usage of line continuation is strongly advised in the original netlist.
- Immediate set options and deferred set options are partially covered.


## Usage

The syntax for the Spectre to Eldo Converter tool is as follows:

```
spect2el
-in_dir <dir1>
[-file_list <list>]
[-out_dir <dir2>]
[-log <file>]
[-remove_param 1|0]
[-remove_param_warn 1|0]
[-do_va 1|0]
[-inline_warnings 1|0]
[-netlist_converter 1|0]
[-devx 1|0]
[-scs2lib 1|0]
[-condition 2|1|0]
[-database_dir <db_dir>]
[-plot 2|1|0]
[-s2emode 2|1]
[-css 1|0]
```

All the above arguments are optional except for -in_dir.
-in_dir dir1
-file_list list

Input directory where the library/netlist to be converted reside. This could be a full path or a relative path, relative to where the tool is initiated. Required.

File list to be converted. It defaults to all files in the given directory if not specified. Default '*'.

## Note

The file list should only include the library main file(s), which is to be directly included in the netlist in case of library conversion, or only the netlist file in case of netlist conversion. Other files, which are included from within those main file(s) are handled automatically. In other words, each file in the file list should not be included in any other file in the file list.

## Note

Each file in the file list should be a standalone file. It should not depend on any other file in the file list. That is, it should not use any model, parameter, subcircuit, which is not defined in it or in any of the files it includes.
-out_dir dir2
$-\log$ file
-remove_param 1|0

Output directory where the converted files are to be written. This could be a directory name or a path. This directory will be created by the tool. If this directory already exists a warning message is issued. If not specified, it defaults to the same name as the input directory name but with a suffix "_converted." Default./\{in_dir\}_converted for output name.

Specifies the log file that contains a brief report about the conversion process including any error or warning messages appearing during the conversion. If not specified, it defaults to a file named spect2el.log in the current working directory. The file can be specified by name, or by full path, or relative path to the current working directory.

If set, it will remove some model card parameters which are not supported by Eldo. Default 1 (set). If set, parameters removed are: "dope" for Diode level 1. "meto" and "wnoi" for BSIM3v3.
-remove_param_warn 1|0 If set, a warning will be issued each time one of the above parameters is removed. (This works only if -remove_param is set.) Default 0 (not set).

Attempts to convert Verilog-A instances used inside SPICE netlists. (Note, this feature is not $100 \%$ guaranteed. Its success is dependent on the syntax of the Verilog files included. Any unusual syntax in the Verilog file may cause
-inline_warnings $1 \mid 0$
-netlist_converter $1 \mid 0$
-devx $1 \mid 0$
this feature to fail. Any issue regarding Verilog syntax is beyond the scope of this converter.) Default 1 (set).
-inline_warnings 1|0 Useful converter warnings will be printed inline as comments in the converted netlist to ease any required manual conversion work. Default 0 (not set).

Enable the netlist conversion feature. Default 1 (set).
Control whether the mismatch variation (for Monte-Carlo analysis) in Spectre would be converted to devx variation (set to 1 ) or $d e v$ variation (set to 0 ) in Eldo. Default is 1 which means that it would be converted to devx.

Enable the feature of converting all files with extensions .scs to have the extension .lib. This also handles all include statements. Default 0 (not set). To switch it on, set this option to 1 .

Controls the conversion of Spectre statements that include the conditional operator "?" as below:
if -condition 0 , the converter will parse the conditional statement as is (default). if -condition 1, the converter will use keyword eval in the conversion (pre-2008.2 behavior).
if -condition 2 , the converter will use keyword valif in the conversion.
-database_dir db_dir
-plot $2|1| 0 \quad$ Controls the conversion of Spectre save statements into Eldo .PRINT, .PLOT and .PROBE commands as below:
if -plot 0 , the converter will convert the save statement into .PRINT (default).
if -plot 1 , the converter will convert the save statement into .PLOT.
if -plot 2, the converter will convert the save statement into .PROBE.
-s2emode 2|1
-css $1 \mid 0 \quad$ Used to choose either to convert all sections of your library or just convert the selected sections. Set to 0 (default) convert all sections. Set to 1 to convert only selected sections. (Note: setting to 1 might cause speed loss in some cases.)

Display the tool usage.

## Usage Examples

The following is an example of converting a design including the library:

```
spect2el -in_dir . -out_dir ./out -file_list netlist.scs -plot
```

The following is an example of converting a library:

```
spect2el -in_dir . -out_dir ./out -file_list allModels.scs -scs2lib 1
```

In both cases, the output directory out will be created if it does not already exist. A directory named external files will be created in the directory out for converted . IIb/. Include files.

## Appendix A Error Messages

## Error Message Classification

When an error is detected during parsing of the simulation input file, a message is printed out specifying:

- The source line number.
- The text containing the error.


## Warnings

Warnings may be caused by improper use of commands or parameters which are then ignored by the analyzer. A warning does not prevent the continuation of analysis and simulation. By default, Eldo displays each type of node connection fault warnings (107, 108, 113 and 252) only three times; to override this default use the MSGNODE option.
(1) For more information on this option, please refer to "MSGNODE=VAL" on page 996.

## Syntax Errors

Error messages usually result from commands or parameters which are not recognized by the analyzer. When a syntax error is detected the simulation does not continue. It is then necessary to edit <circuit>.cir and correct the syntax error. In the printout <circuit>.chi, the error location in the text is indicated by a " $\wedge$ " character, possibly accompanied by a message. The source line number and the source line may not be indicated if the syntax error is detected on a global basis without reference to a particular line.

## Effects

In the event of a warning, execution continues. If a syntax error is detected on the first analysis step (lexical and syntax analysis), circuit parsing continues until the end of this step, otherwise execution is aborted immediately. The numbers of errors and warnings found are displayed at the end of the first and second step.

## Note

 After an error has been detected by the analyzer, subsequent error messages may be unfounded. It is therefore recommended to modify the source file to eliminate the first error before attempting to interpret the other messages.

## Error Messages

## Global Errors

Table A-1. Global Errors

| Error <br> Number | Description |
| :--- | :--- |
| Error 1 | Unable to open the file name |
| Error 2 | Unable to open the library file name |
| Error 5 | Unable to open the temporary file name |
| Error 6 | Nested \#com statements are not allowed |
| Error 7 | Unable to delete the temporary file name |
| Error 9 | Internal error in AC analysis |
| Error 10 | Non invertible matrix |
| Error 11 | Bad execution of name |
| Error 12 | Check sum incorrect. Check your key |
| Error 13 | Error in reading key: (number). Check your key |
| Error 14 | Error in reading ADC/DAC; file name not specified |
| Error 15 | The environment variable USER is not set by the system. Set this variable in your <br> .cshrc or .login script |
| Error 16 | Unable to allocate number bytes. Memory already allocated name |
| Error 17 | MEMALLOC: Unable to allocate number bytes. Memory already allocated name |
| Error 18 | MAMALLOC: Unable to allocate number bytes. Memory already allocated name |
| Error 19 | Unable to load file name. Analysis stopped |
| Error 20 | The number of plots of the current simulation does not match the number of plots <br> of the previous one. File reading stopped |
| Error 21 | Storage capacity exceeded. Memory already allocated name, eldo_mem_used() |
| Error 22 | Circuit nesting error |

Table A-1. Global Errors

| Error <br> Number | Description |
| :--- | :--- |
| Error 23 | Unrecognized character or word |
| Error 24 | Unexpected end of file |
| Error 25 | Line not consistent with language syntax |
| Error 26 | No analysis specified |
| Error 27 | Inductor/Voltage source loop found <br> To allow a voltage loop made up of 0 voltage sources use .OPTION LOOPV0 <br> To downgrade this error to a warning use .OPTION <br> VOLTAGE_LOOP_SEVERITY = WARNING <br> Voltage loops may lead to singular matrix during simulation |
| Error 28 | Unable to reallocate name |
| Error 30 | Mismatch in model specification for device name |
| Error 31 | DATA or SWEEP specification: name |
| Error 32 | Switch option cannot be used on device name |
| Error 34 | .OPTIMIZE MOD: no parameter specified |
| Error 36 | .OPTION LVLTIM must be 1, 2, 3, or 4 |
| Error 38 | Compilation errors in file name |
| Error 39 | Not enough memory to handle waves created through the DEFWAVE command |
| Error 40 | FML.exe not found |
| Error 41 | name: Real value expected |
| Error 42 | name: Non-real expression expected |
| Error 43 | Only DC followed by TRANSIENT analysis is allowed. |
| Error 44 | FasC model name already defined |
| Error 45 | .OPTION DVDT must be -1 or 0. |
| Error 46 | No plot to display for name analysis: Simulation stopped. |
| Error 47 | Error in updating the library. Refer to file name |
| Error 48 | No voltage or current AC input source specified |
| Error 49 | Unable to spawn name: There might not be enough memory |
| Error 50 | .OPTION NEWTON and OSR are not compatible |
| Error 51 | No plot matching analysis type: Analysis stopped. |
| Error 52 | No node "0" found in the circuit |

Table A-1. Global Errors

| Error <br> Number | Description |
| :--- | :--- |
| Error 54 | Syntax error parsing name |
| Error 55 | The following line is too long |
| Error 56 | No key to run name |
| Error 57 | Nested DC Sweeps are not allowed within SimPilot |
| Error 58 | Error: Command name not allowed within SimPilot |
| Error 59 | No value given for parameter name |
| Error 60 | Real value expected for name: End of line found |
| Error 61 | .OPTION IEM and OSR are not compatible |
| Error 62 | .OPTION IEM and NEWTON are not compatible |
| Error 63 | Unable to include file name |
| Error 64 | .MODDUP cannot be used in conjunction with LOT\|DEV |
| Error 65 | .MODDUP cannot be used in conjunction with .MC |
| Error 66 | .OPTION HMIN: Value must be strictly positive |
| Error 67 | .OPTION LVLCNV must be 0, 2, or 3 |
| Error 68 | COMMAND .INCLUDE/.LIB cannot find name |
| Error 69 | Cannot find HDLA models |
| Error 70 | .OPTION name expects an integer value |
| Error 71 | TUNING: Unexpected parameter name |
| Error 72 | Probable syntax error in library name |
| Error 73 | Fatal error in name model, please check output file for details. Eldo Kernel can't <br> find the 'SBVAL.PAR' file |
| Error 74 | Cannot find \#endcom statement |
| Error 75 | ADVance MS command must be used in place of Eldo in order to use <br> VHDL-AMS models <br> Error 76 Internal error: Mismatch in parameter name |
| Error 77 | Line not allowed inside command file |
| Error 78 | Unknown command name |
| Error 79 | DEBUG command number name not found |
| Error 80 | .RUN: Unknown argument name |
| Too many files opened |  |

Table A-1. Global Errors

| Error <br> Number | Description |
| :--- | :--- |
| Error 82 | Parameter not known: name |
| Error 83 | Unable to alter name |
| Error 84 | Missing parameters |
| Error 85 | Syntax error or <br> Syntax error at or near name |
| Error 86 | Error evaluating name |
| Error 87 | Command cannot be issued at run time, or <br> Command name cannot be issued at run time |
| Error 88 | name cannot change .MODEL card for that kind of element |
| Error 89 | name disabled because AC analysis performed within transient analysis. <br> However, with keyword ALL added on the .MC card, simulation should run |
| Error 90 | SST analysis cannot be performed: Device name is not supported |
| Error 91 | SST analysis cannot be performed: Gudm model on name not supported |
| Error 92 | SST analysis cannot be performed: MOS model on name should be a charge- <br> controlled model |
| Error 93 | SST analysis cannot be performed: Non-Quasi Static effects on name is not <br> supported |
| Error 94 | Unknown directive: name |
| Error 95 | No matching keyword name |
| Error 96 | Parameter name cannot be evaluated |
| Error 97 | Mismatch between .iic and .cir files: Simulation stopped |
| Error 98 | Having both .STEP and SWEEP on AC/TRAN/DC cards is not allowed |
| Error 99 | Unable to find a .DATA statement named name |
| Error 100 | This version of Eldo does not include name |

## Errors Related to Nodes

The following error messages are preceded by NODE <name>:
Table A-2. Errors Related to Nodes

| Error <br> Number | Description |
| :--- | :--- |
| Error 101 | No source on this node |

Table A-2. Errors Related to Nodes

| Error <br> Number | Description |
| :--- | :--- |
| Error 102 | Multiple input signal applied |
| Error 103 | The DIGITAL to ANALOG Voltage Source Converter conflicts with another <br> Voltage Source already attached to this node |
| Error 104 | Multiple DTOA on this node and at least one of them is a Voltage Source <br> Converter. This is not allowed |
| Error 105 | Inconsistencies in the High Voltage specifications of the different RC DTOA <br> Converters connected to this node |
| Error 106 | Inconsistencies in the Low Voltage specifications of the different RC DTOA <br> Converters connected to this node |
| Error 107 | Node name not known |
| Error 108 | Iout plot specification ignored on top-level nodes |
| Error 109 | This node is a floating gate |
| Error 111 | Less than two connections |
| Error 112 | No DC path to ground |
| Error 113 | A2D/D2A cannot be applied on non-existing nodes |
| Error 114 | Connectivity around that node makes Matrix singular |
| Error 115 | Related device not found |
| Error 116 | Only IN port seen, and no signal applied |
| Error 117 | Missing A2D/D2A to connect to object |

## Errors Related to Objects

The following error messages are preceded by ОВЈЕСт <name>:
Table A-3. Errors Related to Objects

| Error <br> Number | Description |
| :--- | :--- |
| Error 201 | Cannot be used in AC analysis, or <br> Cannot be used with CAPTAB |
| Error 202 | AC input has not been found |
| Error 203 | Parameter sweep not available for this object |
| Error 204 | VTH1 and VTH2 are inverted |
| Error 205 | Not found in file: name |

Table A-3. Errors Related to Objects

| Error <br> Number | Description |
| :--- | :--- |
| Error 206 | VHI and VLO are equal |
| Error 207 | VHI and VLO are inverted |
| Error 208 | Unrecognized character or word: name |
| Error 209 | Incorrect declaration of POLY names |
| Error 210 | Keyword FREQ expected |
| Error 211 | Parameters are missing |
| Error 212 | Unknown signal type: name |
| Error 213 | Incorrect geometrical dimension: name |
| Error 214 | No value specified for object: name |
| Error 215 | Macro already defined |
| Error 216 | Too many controlling nodes (> 3) |
| Error 217 | Model not yet defined: model_name |
| Error 218 | Model not found: model_name |
| Error 219 | Short circuit element |
| Error 220 | Voltage specifications are missing |
| Error 221 | Is a multidimensional element |
| Error 222 | SIN: Frequency below zero |
| Error 223 | SFFM: FC below zero |
| Error 224 | SFFM: FS below zero |
| Error 225 | EXP: TAU1 below zero |
| Error 226 | EXP: TAU2 below zero |
| Error 227 | Unknown signal applied |
| Error 228 | Either TD or F must be specified |
| Error 229 | Multidimensional object. This variable is not declared |
| Error 230 | Output pin is already a voltage source |
| Error 231 | Output pin is already connected to a comparator output |
| Error 232 | Geometries are below zero: please check DW and DL |
| Error 233 | Value becomes zero. Exited |
| Error 234 | Syntax error in the expression |

Table A-3. Errors Related to Objects

| Error <br> Number | Description |
| :--- | :--- |
| Error 235 | Brackets are missing in the TABLE values |
| Error 236 | Table input values must be properly ordered |
| Error 238 | Bus specification ignored |
| Error 240 | A time or a value specification is missing for this bus |
| Error 242 | This bus is already defined |
| Error 244 | A signal has been already applied on this bus |
| Error 245 | More than one .CHECKBUS applied on this bus |
| Error 246 | No model specified in this functional call: name |
| Error 248 | Unable to plot the capacitances of this device. Only charges are available |
| Error 250 | Unable to plot the charges of this device. Only capacitances are available |
| Error 251 | Unexpected character found |
| Error 252 | Parameters or pins are missing for this device |
| Error 253 | Is not accessible |
| Error 254 | Unknown parameter: name |
| Error 255 | Unknown keyword: name |
| Error 256 | The sign : is missing after keyword |
| Error 257 | '‘ found when not expected |
| Error 258 | Element not found: name |
| Error 259 | The following element is not a current source: name |
| Error 260 | The following element is not a voltage source: name |
| Error 261 | Pin not found: name |
| Error 262 | Number of pins: number |
| Error 263 | Number of controlling nodes: number |
| Error 264 | Number of controlling zero voltage sources: number |
| Error 265 | Number of controlled voltage sources: number |
| Error 266 | Number of controlled current sources: number |
| Error 267 | Number of parameters: number |
| Error 268 | Error when initializing SOLVE routines |
| Error 269 | Error when initializing INTEGRAL routines |

Table A-3. Errors Related to Objects

| Error <br> Number | Description |
| :--- | :--- |
| Error 270 | Parameter not found |
| Error 271 | Duplicate definition of parameter: name |
| Error 272 | Parameter already assigned to an equivalent: name |
| Error 273 | Parameter index not found: name |
| Error 274 | Error in macro name |
| Error 275 | VSTATUS already called with different pin order on: name |
| Error 276 | Unable to apply the function: name |
| Error 277 | Unable to find previous state: name |
| Error 278 | Error in function |
| Error 279 | No model assigned to this element |
| Error 280 | Model attached to this device is also attached to another device of a different type |
| Error 281 | Its model is also attached to the following component: name |
| Error 282 | Access resistor becomes less than or equal to zero |
| Error 283 | Error when computing R value. Division by 0 |
| Error 284 | Keyword PARAM expected instead of: name |
| Error 285 | Equal sign '=' expected instead of: name |
| Error 286 | Unknown Base specification |
| Error 287 | Cannot get the current through non-voltage source |
| Error 288 | Unable to parse expression of |
| Error 289 | Radiation source not found |
| Error 290 | SOI back source not found |
| Error 291 | Radiation source specification error |
| Error 292 | SOI back source specification error |
| Error 293 | The current through cannot be used as argument |
| Error 294 | Inconsistency in voltage specification |
| Error 295 | Unexpected digit found in the bus: name |
| Error 296 | Unable to code |
| Error 297 | Unknown pin number |
| Error 298 | R value is missing |

Table A-3. Errors Related to Objects

| Error Number | Description |
| :---: | :---: |
| Error 299 | Mismatch in POLY specification |
| Error 801 | Parameterizable object not created |
| Error 802 | This RC line refers to a model which is already attached to a standard resistance: name |
| Error 803 | This resistance refers to a model which is already attached to an RC line: name |
| Error 804 | Probably an RC line: please, specify level $=3$ in the relevant .MODEL card |
| Error 805 | Missing model specifications |
| Error 806 | Delay cannot be 0.0 |
| Error 807 | .PLOTLOG: Specified object is not 0xx instance |
| Error 808 | .PLOTLOG: Functional instance not defined |
| Error 809 | BSIM1: Parameter K1 $=$ K10 + K1L/Leff + K1W/Weff $<=0.0$. Check your model card or the transistor dimensions. |
| Error 810 | .PBOUND: syntax is .PBOUND <pname> (mini,maxi) |
| Error 812 | Object not yet created |
| Error 813 | According to parameters specified, a model must be assigned to this device |
| Error 814 | This device refers to an inconsistent model |
| Error 815 | Inconsistency in thresholds/voltages declarations |
| Error 816 | The thresholds must be in the range [VLO + 1\%, VHI - 1\%] |
| Error 817 | The BS value for that core must be greater than the BS value |
| Error 818 | The HC value for that core must be greater than zero |
| Error 819 | The temperature-adjusted BS value for that core must be greater than zero |
| Error 820 | The temperature-adjusted BR value for that core must be greater than zero |
| Error 821 | The temperature-adjusted HC value for that core must be greater than zero |
| Error 822 | The temperature-adjusted BS value for that core must be greater than the temperature-adjusted BR. |
| Error 823 | AREA must be greater than 0 |
| Error 824 | FAS syntax expected on this element: HDL-A syntax found |
| Error 825 | HDL-A syntax expected on this element: FAS syntax found |
| Error 826 | LENGTH and AREA must be strictly positive |
| Error 827 | Mismatch in port specification |

Table A-3. Errors Related to Objects

| Error <br> Number | Description |
| :--- | :--- |
| Error 828 | Equal sign ' $=$ ' is missing in parameter list |
| Error 829 | Unexpected equal sign ' $=$ ' in parameter list |
| Error 830 | Several ports with that index |
| Error 831 | No port index specified |
| Error 832 | Missing R value |
| Error 833 | device_name COUPLING: expecting keyword I or V: found name |
| Error 834 | Syntax error in PATTERN command |
| Error 835 | Object Error |
| Error 836 | Mismatch in coupling specification |
| Error 838 | Already defined |
| Error 839 | No model assigned to that device (MODDUP) |
| Error 840 | Short circuit on dipole device |
| Error 841 | This element cannot be converted into its switch equivalent |
| Error 842 | Odd number of pins |
| Error 843 | Declaration of that object must be put at the very end of the netlist, since it is <br> connected to hierarchical nodes, otherwise the node may not exist yet. <br> Error 844 Pin specification is missing |
| Error 855 | TDEV should be specified on that device |
| Error 856 | Syntax HDLA_NAME = ELDO_NAME expected |
| Error 857 | Multiple SST specifications |
| Error 858 | Wrong object inside thermal network: only R/V/C device type can be specified |
| Error 859 | AREA/PERI and W/L cannot be given together |
| Error 860 | Multiple types of input applied |
| Error 861 | Not declared |
| Error 862 | Unable to mix FPORT syntax with RPORT syntax. FPORT must be replaced by a |
| voltage current source with R/C/L specifications. |  |
| Error 866 | First pin of that element is undefined |
| Error 863 | RPORT can be applied on voltage source only |
| Error 864 | Missing IPORT specification |
| Error 865 | AREA is negative or 0.0 |

Table A-3. Errors Related to Objects

| Error <br> Number | Description |
| :--- | :--- |
| Error 867 | Second pin of that element is undefined |
| Error 868 | .TRAN and .FOUR specification is not allowed on the same device |
| Error 869 | Level not specified for geometric model |
| Error 870 | Generic/Parameter field appears twice |
| Error 871 | Only 'VALUE', 'TABLE' or 'AC' arguments expected |
| Error 872 | Device not found |
| Error 873 | Missing L or W specification to enable appropriate model selection |
| Error 874 | No character string allowed in Param/Generic list |
| Error 875 | DDT or IDT operator allowed on 'E' or 'G' sources only |
| Error 876 | L and W must be specified before M(<param>) |
| Error 877 | Character not allowed on pattern |
| Error 878 | Value not specified |
| Error 879 | PORTS specification appears more than once |
| Error 880 | PINS specification appears more than once |
| Error 881 | Only PINS specification allowed on VHDL-AMS instances |
| Error 882 | GENERIC specification appears more than once |
| Error 883 | Dimension must be 1 exclusively |
| Error 884 | Second controlling node must be same as the second pin |
| Error 885 | Second controlling node must be same as the first pin |
| Error 886 | Parameters of denominator for S/Z transform are all zero. |
| Error 887 | More than one value specified for resistor value |
| Error 888 | TSAMPLE not specified for PATTERN .CHECKBUS |
| Error 889 | Undeclared inductor |
| Error 890 | Expects syntax PWL(1) N1 N2 MODEL value |
| Error 891 | Syntax error in IBIS model call |
| Error 892 | Unknown IBIS device |
| Error 893 | Component name is missing inside IBIS model call |
| Error 894 | filename is missing inside IBIS model call |
| Error 895 | MODEL and PIN can't be both specified |

Table A-3. Errors Related to Objects

| Error <br> Number | Description |
| :--- | :--- |
| Error 896 | Cannot replace source, discontinuity found |
| Error 897 | Expects an even number of parameters |
| Error 898 | PZ or FNS allowed on E elements only |
| Error 899 | Neither MODEL nor PIN specified |
| Error 900 | FNS denominator cannot be 0 |

## Errors Related to Commands

The following error messages are preceded by COMMAND
Table A-4. Errors Related to Commands

| Error <br> Number | Description |
| :--- | :--- |
| Error 301 | .MC: Monte Carlo analysis is not compatible with .ALTER |
| Error 302 | .MC: Monte Carlo analysis is not compatible with .STEP |
| Error 303 | .ALTER: This command is not compatible with .STEP |
| Error 304 | .MC: Unable to reallocate .MODEL field |
| Error 305 | .MC: Internal memory error |
| Error 307 | .CHRSIM: A previous transient analysis is required for the circuit |
| Error 308 | .CHRSIM: A previous DC sweep analysis is required for the circuit |
| Error 309 | .CHRSIM: No output found in previous circuit to be connected to input |
| Error 310 | .SENS: Unable to create sensitivity matrix |
| Error 311 | .SENS: Circuit size too large (>name) for sensitivity analysis |
| Error 312 | .MC: Type not found |
| Error 313 | .OPTFOUR: Unknown output format |
| Error 314 | .INIT: Time values are missing |
| Error 315 | .IC: Time values are missing |
| Error 316 | .USE name: Specification unknown |
| Error 317 | .TRAN: Parameters are missing |
| Error 318 | .USE name: Specification unknown |
| Error 319 | .PLOT name: This kind of analysis is not supported |

Table A-4. Errors Related to Commands

| Error Number | Description |
| :---: | :---: |
| Error 320 | .LOOP: Object type not allowed: name |
| Error 321 | .PARAM: Attempt to divide by zero |
| Error 322 | .DC: W or L must be written in place of name |
| Error 324 | .OPTIMIZE: Name or element name not yet defined |
| Error 325 | .DC: Too many values specified |
| Error 326 | .RESTART: The file used to restart has the same name as the current circuit. Rename the previous .cou file |
| Error 327 | .OPTIMIZE: name not yet created |
| Error 328 | .OPTIMIZE: Model name not yet created |
| Error 329 | .OPTIMIZE name: Incompatible operation |
| Error 330 | .DC: Unknown object name |
| Error 331 | .OPTIMIZE: AC output node name not yet defined |
| Error 332 | .IC: Error on name |
| Error 333 | .SOLVE: Error in expression |
| Error 334 | .SOLVE: Element name not yet defined. |
| Error 335 | .OPTIMIZE: Parameter name not known |
| Error 336 | .PLOT: Specification name not allowed |
| Error 337 | .DC: Sweep object not specified |
| Error 338 | .OPTIMIZE: Use ACOUT=<pin_name> to select output |
| Error 339 | .NOISETRAN: Error with parameter |
| Error 340 | The Thermal Noise Level (number) is not compatible with values extracted from MOS model |
| Error 341 | .NOISE: Element name not found |
| Error 342 | .SOLVE: Element name not found |
| Error 344 | .MFTA: Parameter name not found |
| Error 345 | .MFTA: Missing argument |
| Error 346 | .SAVE: File name is already specified in a previous .SAVE command |
| Error 348 | .INIT cannot be applied on node name: Conflict of signals |
| Error 350 | .WCASE: Unknown analysis specification name |
| Error 352 | Expression name can accept only items V(node) or I(object) |

Table A-4. Errors Related to Commands

| Error <br> Number | Description |
| :---: | :---: |
| Error 354 | Expression name can accept only items V(node), I(object) or W(w) |
| Error 359 | .PARAM: "=" is missing in expression: name |
| Error 360 | .OPTIMIZE: Unexpected expression: name |
| Error 361 | .EXTRACT: Unexpected expression: name |
| Error 362 | .STEP PARAM: Parameter name not specified |
| Error 363 | .DC: The parameter name is not specified or is not a primitive. Unable to perform this analysis |
| Error 364 | .STEP: Parameter name not defined at the top level |
| Error 365 | .DC PARAM: Parameter name not defined at the top level |
| Error 366 | .ALTER: Appears as the title |
| Error 367 | name: Unknown command |
| Error 368 | .OPTIMIZE: sign $=<>$ expected instead of name |
| Error 369 | .DEFWAVE: Error name = |
| Error 370 | .OPTIMIZE: name not allowed on parameter |
| Error 371 | .PLOTLOG command: '->' sign is missing |
| Error 372 | .PLOT command: Found name while expecting a ( or ) |
| Error 373 | .SETSOA: Opening bracket expected after name |
| Error 374 | .SETSOA: Closing bracket expected after name |
| Error 375 | .SETSOA: Error in the expression name |
| Error 376 | .SETSOA: Expected .SETSOA EXPR <expression> = (MIN,MAX) |
| Error 377 | .SETSOA: Expected a * or a value for name |
| Error 378 | .SETSOA: Model name not yet created |
| Error 379 | .WC cannot be used with command .MC |
| Error 380 | .CONNECT: Node name not yet created. The X instance which creates the node must be placed before the .CONNECT card |
| Error 381 | .SIGBUS: No parameters allowed (name) |
| Error 384 | .DISTRIB name: Opening bracket expected |
| Error 385 | .DISTRIB name: Closing bracket expected |
| Error 386 | .DISTRIB name is already defined |
| Error 387 | name: Specified terms must be properly ordered |

Table A-4. Errors Related to Commands

| Error <br> Number | Description |
| :---: | :---: |
| Error 388 | .DISTRIB name: <probability> must be in the range [0 to 1] |
| Error 389 | Distribution name referenced but not defined |
| Error 390 | Error in LOT/DEV specification for expression name |
| Error 391 | .PARAM: Double specification for name |
| Error 392 | .TRAN: No parameter allowed: (name found) |
| Error 393 | .DISTRIB name: <deviation> must be within the range [-1 to 1] |
| Error 394 | Unable to measure ISUB (name): multiple connections |
| Error 395 | .OPTION name ignored |
| Error 396 | .STEP: DEC, LIN or OCT expected: name found |
| Error 397 | .STEP: No parameter allowed: name found |
| Error 398 | .STEP: DEC/OCT values must be positive |
| Error 399 | name: Negative X value found for DEC scale |
| Error 400 | .LMIN or .WMIN: Parameters are missing |
| Error 401 | .OPTNOISE: Real value expected after keyword name |
| Error 402 | .OPTNOISE: Keywords D V TD TV expected: name found |
| Error 403 | .OPTNOISE: SV: Value must be less than 1 but greater than 0: name found |
| Error 404 | name: The sign ',' is not allowed |
| Error 405 | .SOLVE: Cannot accept functions such as YVAL, TPD, MIN, MAX and INTEG |
| Error 406 | .EXTRACT name: Cannot find a .EXTRACT with this label |
| Error 407 | .OPTFOUR: Unknown parameter: name |
| Error 408 | .EXTRACT name: Cannot find a .FOUR with the label name |
| Error 409 | .SNF: Unknown parameter name |
| Error 410 | .SNF: Double input specification for name field |
| Error 411 | Multiple .SNF cards not allowed |
| Error 412 | .SNF card: name specification expected |
| Error 413 | .FOUR card: Syntax is [LABEL=] <four_label> <wave> |
| Error 414 | .EXTRACT name: RMS accepts transient waves or AC noise waves only |
| Error 415 | .OPTWIND or .OPTPWL: Parameter name cannot be changed |
| Error 416 | .OPTWIND or .OPTPWL: Missing time-value for name |

Table A-4. Errors Related to Commands

| Error Number | Description |
| :---: | :---: |
| Error 417 | .OPTWIND or .OPTPWL: Decreasing time-value for name |
| Error 418 | .AC: Syntax error card: name |
| Error 419 | .OPTWIND or .OPTWPL: Missing value specification at or near name |
| Error 420 | .OPTWIND or .OPTWPL: name |
| Error 421 | IFT: Unexpected argument name |
| Error 422 | .OPTNOISE: NOISE and NONOISE cannot both be specified |
| Error 423 | .OPTNOISE: ALL=OFF and NONOISE cannot both be specified |
| Error 424 | .OPTNOISE: ALL=ON and NOISE cannot be both specified |
| Error 425 | .SNF: Element name not found |
| Error 426 | .SNF: Element name appears as both input and output |
| Error 427 | .OPTFOUR: Parameter FS must be specified |
| Error 428 | .PZ: This analysis might give unexpected results because several AC sources are found in the circuit |
| Error 429 | .ALTER: Not allowed in Accusim netlist |
| Error 430 | .NOISETRAN: Too many runs specified |
| Error 431 | .OPTFOUR: Bad value for parameters TSTART, TSTOP, NBPT and FS |
| Error 432 | .STEP PARAM ( ): Syntax error |
| Error 433 | .STEP PARAM ( ): Only LIST allowed for multi step |
| Error 434 | .STEP PARAM ( ): The number of values does not match the number of parameters |
| Error 435 | .STEP: TEMP keyword cannot appear more than once |
| Error 436 | .STEP: Unknown name |
| Error 437 | .CHECKSOA: Unexpected parameter |
| Error 438 | .SETSOA: Expecting D, E or M: name found |
| Error 439 | .STEP: Missing increment parameter |
| Error 440 | .STEP: Missing boundary specification |
| Error 441 | .WCASE: Missing analysis specification |
| Error 442 | .AC LIST: Frequencies are not properly ordered |
| Error 443 | .DC: Only a real value is expected |
| Error 444 | .DEFWAVE: Duplicate definition of name |

Table A-4. Errors Related to Commands

| Error <br> Number | Description |
| :---: | :---: |
| Error 446 | .OPTFOUR: Unexpected expression: name |
| Error 447 | .DEFMAC: Recursive definition of name |
| Error 448 | .OPTFOUR: The expression for name could not be evaluated |
| Error 449 | .OPTFOUR: TSTART > TSTOP |
| Error 450 | .STEP LIST: name |
| Error 451 | .NOISETRAN: Cannot be used with .OPTION SAMPLE |
| Error 452 | .MEAS: Unknown analysis type name |
| Error 453 | .MEAS: Unknown function name |
| Error 454 | .MEAS: Unexpected wave name |
| Error 455 | .MEAS: Unexpected keyword: name |
| Error 456 | .MEAS: Missing keyword: name |
| Error 457 | .MEAS name: Cannot find a .MEAS of that name |
| Error 458 | .MEAS name: LAST not accepted |
| Error 459 | .DC: name unknown |
| Error 460 | .STEP: Increment is 0.0 |
| Error 461 | .SETSOA: unexpected keyword name |
| Error 462 | .EXTRACT: FILE=name must be placed before the expression |
| Error 463 | .STEP: multiple declaration for name |
| Error 464 | .MCDEV: syntax E(devname[,geo]) expected |
| Error 465 | .TRAN: decreasing time not allowed: name |
| Error 466 | .LOTGROUP: double specification for name |
| Error 467 | .FFT: Syntax is .FFT <wave> < FFT parameters> |
| Error 468 | .PLOTBUS: specification error on name |
| Error 469 | .MODEL name HOOK: syntax is .MODEL <name> HOOK [<logical_lib_name>:]<entity_name>[(<architecture_name>)] |
| Error 470 | .MC specification on name: dead-zone too large compared to 'normal' zone |
| Error 471 | Directive error name |
| Error 472 | .PLOT: SMITH chart available for AC only |
| Error 473 | .SETBUS: node name does not exist |

Table A-4. Errors Related to Commands

| Error <br> Number | Description |
| :---: | :---: |
| Error 474 | .AC expecting DEC, LIN, OCT, LIST or DATA: name found |
| Error 475 | .PART: Unknown flag: name |
| Error 476 | .PART: Syntax error. Syntax is .PART <flag> SUBCKT\|INST (<list>) |
| Error 477 | .SETBUS: node name does not exist |
| Error 478 | .EXTRACT: such SST output .H extensions |
| Error 479 | .HOOK: expects 'MOD=' statement |
| Error 480 | .LOOP: unexpected string name |
| Error 481 | .DEFWAVE name: expects .H extensions |
| Error 482 | name: expects an integer value |
| Error 483 | name: missing a '(' bracket |
| Error 485 | .STEP: step windows must be separated |
| Error 486 | Two ports are required for getting RNEQ/NFMIN_MAG/GOPT/ GAMMA_OPT/GAMMA_OPT_MAG/PHI_OPT/NC |
| Error 487 | .SNF: error specifying SIDEBAND: name |
| Error 488 | .PARAMOPT name 3 or 4 values expected |
| Error 489 | .PLOT: (SMITH) or (SPECTRAL) incompatible with (VERSUS) |
| Error 490 | .PLOT: (VERSUS) must be followed by only one wave. |
| Error 491 | .PLOT: No wave found before (VERSUS) |
| Error 492 | .TVINCLUDE: syntax error in test vector name |
| Error 493 | .DATA: name: Unable to open file name |
| Error 494 | .EXTRACT: name: LABEL = <> expected |
| Error 495 |  |
| Error 496 | .SNF: name |
| Error 497 | name not allowed with Mach |
| Error 498 | .PRINT/PLOT/PROBE/EXTRACT: bad number of tones specified |
| Error 499 | .CORREL: parameter name cannot be found |
| Error 500 | .CORREL: Instance name cannot be found |

## Errors Related to Models

The following error messages are preceded by MODEL:
Table A-5. Errors Related to Models

| Error <br> Number | Description |
| :--- | :--- |
| Error 501 | Not found in library |
| Error 502 | Unknown in the libraries |
| Error 503 | Undeclared model reference |
| Error 504 | Is defined twice |
| Error 505 | Parameter unknown |
| Error 506 | Model not yet defined |
| Error 507 | Inconsistency in level specification. LEVEL: number |
| Error 508 | Level not implemented |
| Error 509 | R model not declared |
| Error 510 | NSUB < NI. exited |
| Error 511 | C model not declared |
| Error 512 | G model not declared |
| Error 514 | BIDIR type not allowed. Use ATOD or DTOA |
| Error 515 | Default BIDIR Converter not found |
| Error 516 | LEVEL already specified |
| Error 517 | Parameter TOX must be greater than 0 |
| Error 518 | Parameter STRUCT must be +1 or -1 |
| Error 519 | Unacceptable parameter value |
| Error 520 | MJSW must be less than 1.0 |
| Error 521 | N must be positive |
| Error 522 | FC must be less than 1.0 |
| Error 523 | The following parameter must only be used when eldomos is active or level 12 or |
| 13 are used |  |
| Error 524 | Model Error |
| Error 526 | Unable to alter the parameters of that model |
| Error 527 | This model is used by Eldo-XL and cannot be replaced |

Table A-5. Errors Related to Models

| Error <br> Number | Description |
| :--- | :--- |
| Error 528 | This model cannot be changed using .LIB in an interactive mode: Inconsistent <br> level or architecture |
| Error 529 | The following parameter cannot be used with model MM9 |
| Error 530 | Unknown language type |
| Error 531 | Double MC specification (via .MCMOD/.MODEL) for the parameter name |
| Error 532 | Expects PWL(1) SYMMETRY NO SOURCE CARDS DATA |
| Error 533 | Parameter COX cannot be specified for that model |
| Error 534 | W model: missing declaration of parameter N |
| Error 535 | W model: incorrect number of parameters |
| Error 536 | parameter name already assigned |
| Error 537 | vector size not consistent for parameter name |
| Error 538 | Missing inout values for parameter name |
| Error 539 | Size of vectors not consistent |
| Error 540 | Missing call to MP_vect_array |
| Error 541 | inconsistent dimension of the vector array |
| Error 542 | Position already allocated |
| Error 543 | PASSFAIL/BISECTION expected after METHOD parameter |
| Error 544 | DEVX specification cannot be applied on .MODEL parameters |
| Error 545 | This level is not supported yet |

## Errors Related to AMODELS

The following error messages are preceded by amodel <name>:
Table A-6. Errors Related to AMODELS

| Error <br> Number | Description |
| :--- | :--- |
| Error 601 | Attempt to redefine an Amodel while the previous definition is not completed |
| Error 602 | Definition not completed |
| Error 603 | Macromodel not found |
| Error 604 | Pins must be specified before Ports |

## Errors Related to Subcircuits

The following error messages are preceded by SUBCKT <name>:
Table A-7. Errors Related to Subcircuits

| Error <br> Number | Description |
| :--- | :--- |
| Error 701 | Not found in library |
| Error 702 | Undeclared subcircuit reference |
| Error 703 | is defined twice |
| Error 704 | Cannot be declared before the previous one has finished |
| Error 705 | Incorrect number of nodes in call at line |
| Error 708 | Recursive .SUBCKT calls are not allowed |
| Error 709 | Unable to connect the output to a power supply or another digital output |
| Error 710 | Error in declaration |
| Error 711 | Already obtained from another LIB file |
| Error 712 | Cannot define a parameter named 'M' |
| Error 713 | An 'IF' statement is not properly closed |
| Error 714 | Unexpected keyword name |
| Error 715 | refering to non-existing hierarchical node |
|  |  |

## Miscellaneous Errors

Table A-8. Miscellaneous Errors

| Error <br> Number | Description |
| :--- | :--- |
| Error 901 | number: Unknown signal type at line |
| Error 902 | name: Unknown parameter |
| Error 903 | name: Specification ignored |
| Error 904 | name: Unknown model type |
| Error 905 | name: Parameter not found |
| Error 906 | name: Unknown output format specified |
| Error 907 | name: Can not affect value |
| Error 908 | name: Parameter not yet set |

Table A-8. Miscellaneous Errors

| Error <br> Number | Description |
| :---: | :---: |
| Error 909 | name: Unknown specification |
| Error 910 | name: Model not yet defined |
| Error 911 | Diagram not supported at line |
| Error 912 | name: Unknown command or component at line |
| Error 913 | Decreasing time on input signal number name |
| Error 914 | Decreasing time on input signal assigned to object |
| Error 915 | CFAS: Call to get_param_value() allowed in ALLOCATE MODE only |
| Error 916 | CFAS: Call to get_param_value_b4() not allowed |
| Error 917 | Unable to read from file name |
| Error 918 | Cannot reallocate component table |
| Error 919 | Cannot reallocate input signal |
| Error 920 | Unable to parse expression name |
| Error 921 | name is not specified in ATOD model |
| Error 922 | Description of DTOA name is missing |
| Error 923 | DTOA name is declared as ATOD |
| Error 924 | Description of ATOD name is missing |
| Error 925 | ATOD name is declared as DTOA |
| Error 926 | Error in expression name. I or V expected |
| Error 928 | BIDIR name is declared as ATOD or DTOA |
| Error 929 | MODPAR: Parameter name not known |
| Error 930 | MODPAR: Parameter name is missing |
| Error 931 | EVAL: Parameter name is missing |
| Error 932 | EVAL: Parameter name not known |
| Error 933 | Error in TRISE or TFALL or TCROSS specification |
| Error 934 | .NOISE output must be a node voltage (V(xx)) |
| Error 935 | .PBOUND: parameter name not found |
| Error 936 | name Inconsistent FAS instance |
| Error 937 | .LIB: keyword 'KEY =' expected: name found |
| Error 938 | .MCMOD: expecting LOT or DEV keyword: name |

Table A-8. Miscellaneous Errors

| Error <br> Number | Description |
| :---: | :---: |
| Error 939 | name Unknown .PLOT/.PRINT specification |
| Error 940 | .CHECKSOA: Not compatible with name |
| Error 941 | name cannot be redefined in a .PARAM statement |
| Error 942 | .CHRSIM name: Unknown argument |
| Error 950 | Missing FPORT number name |
| Error 951 | .FFILE: expecting unit (Hz, KHz, MHz, GHz): name found |
| Error 952 | .FFILE: expecting format MA or RI: name found |
| Error 954 | .PZ: expecting V(pin) or I(Vxx) |
| Error 955 | Missing state name to be displayed for device name |
| Error 956 | .TEMP: real value expected, name found |
| Error 957 | .FFILE: expecting S/Y/Z: name found |
| Error 958 | .ALTER inside .INCLUDE is not allowed |
| Error 959 | .PLOT (LOW, HIGH) values must be real: name found |
| Error 960 | .SETSOA: Unexpected keyword 'ELSE' found |
| Error 961 | .SETSOA: source line name: Error in nesting IF-ENDIF statement |
| Error 962 | PORT name has only one connection |
| Error 963 | name: Invalid expression for .EXTRACT DC |
| Error 964 | Port specification in PLOT/PRINT is larger than the number of declared PORTS |
| Error 965 | Inconsistent number of pins for devices name |
| Error 966 | M factor is less than or equal to zero for device name |
| Error 967 | .LIB: .LIB KEY=name already exists |
| Error 968 | Instance already defined: name |
| Error 969 | Unknown MC specification name |
| Error 970 | Missing MC specification in name |
| Error 971 | name: Parameter name cannot start with a digit |
| Error 972 | FNS order must be an integer: name found |
| Error 973 | .LIB: Unable to find library or variant |
| Error 974 | LOTGROUP name not defined |

Table A-8. Miscellaneous Errors

| Error <br> Number | Description |
| :---: | :---: |
| Error 975 | FOUR output: .H extension expected on the wave name |
| Error 976 | Too many simulation are required ( > ELDO_LONGVAL) |
| Error 977 | .H extension on wave: only integer value expected: name found |
| Error 978 | name |
| Error 979 | IBIS: name |
| Error 980 | IBIS: bad value specified for parameter name |
| Error 981 | value cannot be negative |
| Error 982 | Optimization cannot work when command name is active |
| Error 983 | a non FFT output name appears in a FOUR or FOURMODSST extract |
| Error 984 | unmatched if/else/then statement at or near line name |
| Error 985 | Unable to alter parameter name because it controls device instantiation |
| Error 986 | Entity name affected by both MC and a non-MC change |
| Error 987 | .CHRISM: unexpected input format: name |
| Error 988 | .NET: name |
| Error 989 | At least two values are needed |
| Error 990 | .MPRUN: name |
| Error 991 | .EXTRACT mode |
| Error 992 | Parameter name is not allowed |
| Error 993 | Unable to create/alter PORT structure on elements name which have not been instantiated with PORT information in the netlist |
| Error 994 | Parameter name should not contain boolean operator |
| Error 995 | Parameter name should not contain any special characters |
| Error 996 | .EXTRACT: wave name is incompatible with extract analysis |
| Error 997 | .CORREL: need at least 2 name to generate a correlation |
| Error 998 | .DSPMOD: name |
| Error 999 | .DSP: Syntax error in waveform definition |
| Error 1000 | Using a parameter both in OPTIMIZATION and STEP is not allowed |
| Error 1501 | This circuit exhibits singularity, due to ... |
| Error 1502 | .OPTION DSCGLOB: unexpected specification name |

Table A-8. Miscellaneous Errors

| Error <br> Number | Description |
| :--- | :--- |
| Error 1503 | .OPTION parameter DSCGLOB disabled. Use now DSCGLOB = X or <br> DSCGLOB = GLOB |
| Error 1504 | .STEP LIB: name |
| Error 1505 | COMMAND name: |
| Error 1506 | Problem in using ' 1 ' in name |
| Error 1507 | Object name: A periodic source must be associated to PHNOISE |
| Error 3001 | COMMAND .MEAS: duplicate measurement name |
| Error 3002 | OBJECT name: varying parameters can't be used with this object |
| Error 3003 | Unable to open format name |
| Error 3004 | name should be an INTEGER |
| Error 3005 | nesting error inside \#MACHBB directive |
| Error 3006 | \#MACHBB directive must be at top level |
| Error 3007 | Can't find subckt name for macro simulation |
| Error 3008 | Only commands are accepted here |
| Error 3009 | COMMAND .CALL_TCL name |
| Error 3010 | FBLOCK model is not available for HP 64bits version |
| Error 3011 | COMMAND .PARAMOPT: no initial value given |

## Warning Messages

## Global Warnings

Table A-9. Global Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 1 | Mismatch between .iic and .cir files. .RESTART ignored |
| Warning 2 | The restarting values for .RESTART DC are only usable when no DC analysis is <br> required. DC analysis omitted |
| Warning 3 | Unusual simulation time |

Table A-9. Global Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 4 | Due to parameter PTF, the integration scheme has been changed from Trapeze to <br> Backward Euler |
| Warning 5 | unusual value for EPS name |
| Warning 6 | VDS and VGS initializations are useless with Eldo |
| Warning 7 | No output to display |
| Warning 8 | Due to .OPTION SWITCH, the ANALOG specification is ignored |
| Warning 10 | .RESTART: a catenated file |
| Warning 12 | .OPTION EPSDIG ignored due to .OPTION ANALOG |
| Warning 13 | .AC: Values for lower and upper frequencies are inverted |
| Warning 14 | Required 'raw' directory does not exist in the current directory; .OPTION sda $=2$ <br> ignored |
| Warning 15 | AC analysis: name |
| Warning 16 | Digital description ignored in AC analysis |
| Warning 17 | .OPTION TIMEDIV ignored due to .OPTION SIMUDIV |
| Warning 18 | .OPTION EPS set to name |
| Warning 19 | Results from a TRAN analysis are being used for a DC analysis |
| Warning 20 | .OPTION GRAMP accepts only positive integer values below 20 .OPTION |
| GRAMP ignored |  |

Table A-9. Global Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 32 | No FOUR plot to display: FFT analysis removed |
| Warning 33 | XL: VSW0 and VSW1 set to name |
| Warning 34 | UIC specification ignored on .TRAN card in ADMS |
| Warning 35 | Multi-platform MC cannot be used |
| Warning 36 | Unable to open LIB file name |
| Warning 37 | Multiple definition of parameter name |
| Warning 38 | Command name is ignored |
| Warning 39 | First line of the command file must be a comment |
| Warning 40 | .OPTION parmhier: 'local' or 'global' expected |
| Warning 41 | Signals will be displayed in the digital output file |
| Warning 43 | overwriting MIN/MAX of parameter name |
| Warning 44 | .MP not implemented with SST analysis |
| Warning 45 | DATA name |
| Warning 46 | Double definition for parameter name |
| Warning 47 | Unusual value given for name |
| Warning 48 | Multiple .TEMP not allowed in ADMS: only last TEMP value will be used |
| Warning 49 | This circuit exhibits singularity, due to name |
| Warning 50 | name is ignored because of Mach |
| Warning 51 | Using .OPTION RMV0, name zero-voltage sources would have been removed <br> from the database |
| Warning 52 | Optimizer not active with Eldo-demo |
| Warning 53 | Eldo Mach partition UI can't be used in Eldo Mach Black-Box mode |
| Warning 54 | Eldo Mach Black-Box mode disabled because of Eldo Mach partition UI |
| Warning 55 | .OPTION name has been set to |

## Warnings Related to Nodes

The following warning messages are preceded by NODE <name>:
Table A-10. Warnings Related to Nodes

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 101 | Significant node voltage variation, but of a lesser magnitude than VTH at time: <br> number |
| Warning 102 | Number of iterations at time: number |
| Warning 103 | Attempt to redefine .IC |
| Warning 104 | Attempt to redefine .NODESET |
| Warning 105 | Decreasing time on time-values associated to the .IC command |
| Warning 106 | Global node already defined |
| Warning 107 | Less than two connections |
| Warning 108 | This node is a floating gate |
| Warning 109 | This bulk node is not biased |
| Warning 110 | Connected to capacitors only |
| Warning 111 | Less than two connections. Line: number |
| Warning 112 | Connected to grounded capacitors only. This node is removed from the netlist |
| Warning 113 | Not connected to any element. This node is removed from the netlist |
| Warning 114 | Second input signal ignored on that node |
| Warning 115 | This is an ATOD and DTOA node |
| Warning 116 | STRENGTH's CONFLICT on this node. Return to DIGITAL |
| Warning 117 | Not connected to any power supply |
| Warning 118 | No DC path to ground |
| Warning 119 | VTH1 > VTH2 on A2D convertor |
| Warning 120 | VLO > VHI on D2A convertor |
| Warning 121 | Signals will be displayed in the digital output file |
| Warning 122 | DC dangling node |
| Warning 123 | A capacitor of more than 1F is attached to that node |
| Warning 124 | Appears in .CONNECT only |
| Warning 125 | Previous IC value superseded |
| Warning 126 | Previous NODESET/GUESS value superseded |

Table A-10. Warnings Related to Nodes

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 127 | Possibly no DC path on that node |
| Warning 128 | .CONNECT: node not found |
| Warning 129 | has been replaced by a DSPF network |

## Warnings Related to Objects

The following warning messages are preceded by овЈест <name>:
Table A-11. Warnings Related to Objects

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 201 | Cannot be parameterized |
| Warning 202 | Must be a differential amplifier. AC analysis omitted |
| Warning 203 | Object not in the linear domain. AC analysis omitted |
| Warning 204 | Already defined |
| Warning 205 | Unrecognized word: name |
| Warning 206 | No parameter or model specified |
| Warning 207 | Second L value ignored |
| Warning 208 | Second W value ignored |
| Warning 209 | Parameter ignored: name |
| Warning 210 | Z0 set to 50 W |
| Warning 211 | RON set to 1 kW |
| Warning 212 | W is less than WMIN. W is set to WMIN |
| Warning 213 | L is less than LMIN. L is set to LMIN |
| Warning 214 | Value becomes negative |
| Warning 215 | W undefined. Default value is taken: number |
| Warning 216 | L undefined. Default value is taken: number |
| Warning 217 | RS is negative or zero: value reset to |
| Warning 218 | Improper value. Default value is taken (1.0×100). Value: number |
| Warning 219 | Undeclared inductor |
| Warning 220 | Default values used for time specification |
|  |  |

Table A-11. Warnings Related to Objects

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 221 | Instability may occur because some of the root modules of the denominator are <br> greater than 1, (outside the unit z circle). Poles are dumped in the standard <br> output file |
| Warning 222 | Instability may occur because the real parts of some of the denominator's root <br> are greater than 1, (outside the unit z circle). Poles are dumped in the standard <br> output file |
| Warning 223 | Last specification ignored |
| Warning 224 | Parameter already used as an equivalent: name |
| Warning 225 | CPIN already called on pin: name |
| Warning 226 | VSTATUS already called on: name |
| Warning 227 | Resistor value is 0: object not called: name |
| Warning 228 | This resistor is not a RC line. Parameter(s) ignored: name |
| Warning 229 | WEFF=W-2DW too small or negative. Default value RES used |
| Warning 230 | LEFF=L-2DL $\leq 0.0$. Default value RES is used |
| Warning 231 | LEFF and WEFF $\leq 0.0$. Default value CAP is used |
| Warning 232 | DTOA converter: Rhigh is not specified, the default value of 1 mW is taken |
| Warning 233 | DTOA converter: Rlow is not specified, the default value of 1 mW is taken |
| Warning 234 | This element cannot be converted into its switch equivalent |
| Warning 235 | Capacitance value is negative or zero |
| Warning 236 | Node name PARAM:xxxx found: This might be confused with PARAM:xxx |
| Warning 237 | The following dimension has an unusual value: name |
| Warning 238 | .SIGBUS: VHI < VLO |
| Warning 239 | VHI < VLO on .D2A |
| Warning 240 | Object Warning |
| Warning 241 | Unable to plot the capacitances of this device, only charges are available |
| Warning 242 | Unable to plot the charges of this device, only capacitances are available |
| Warning 243 | This object makes reference to the above node, which will be assumed to be |
| ground node 0 |  |

Table A-11. Warnings Related to Objects

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 247 | Capacitance value of more than 1F |
| Warning 248 | There are several ports with that index |
| Warning 249 | The first pin of that element is undefined: Object not created |
| Warning 250 | The second pin of that element is undefined: Object not created |
| Warning 251 | Old syntax: Please use Ixx or Vxx element with PORT specification |
| Warning 252 | Self-connected objected not created. |
| Warning 253 | Parameter PGATE is defined for JUNCAP model only |
| Warning 254 | Differential lines are not supported, the reference plane will be replaced by the <br> ground |
| Warning 255 | Size not consistent with LMIN/LMAX/WMIN/WMAX |
| Warning 256 | Very small value specified. |
| Warning 257 | Values are out of range for |
| Warning 258 | May be diode instantiation was intended, but its name could not start by 'DEL', <br> which is a prefix reserved for Eldo DELAY primitive. |
| Warning 259 | May be CCCS instantiation was intended, but its name could not be started by <br> '/FNZ', which is a prefix reserved for Eldo FNS/FNZ primitive. |
| Warning 260 | May be SUBCKT instantiation was intended, but its name could not be started <br> by ‘XOR', which is a prefix reserved for Eldo XOR primitive. |
| Warning 261 | May be Current Source instantiation was intended but its name could not be <br> started by 'INV', which is a prefix reserved for Eldo INVERTOR primitive |
| Warning 262 | Incorrect value for keyword ABS (1 or 0 expected). Using 0 as default |
| Warning 263 | Ambiguity on parameter name <br> Warning 264Object not yet created <br> Warning 265W or L not specified on that device. Default setting relevant to that model will <br> be used |
| The timestep chosen for the simulation exceeds the delay |  |
| Very small resistors have been encountered. This may cause non-convergence |  |
| problems |  |

## Warnings Related to Commands

The following warning messages are preceded by COMMAND <name>:
Table A-12. Warnings Related to Commands

| Warning Number | Description |
| :---: | :---: |
| Warning 301 | .AC: FREQ1 is set to 1 Hz |
| Warning 302 | .AC: FREQ2 is set to 1 Hz |
| Warning 303 | .IC name: Ignored |
| Warning 304 | .NODESET name: Ignored |
| Warning 305 | .SOLVE: R sweep must be between positive values |
| Warning 306 | .SOLVE: No solution has been found |
| Warning 307 | .SOLVE: No solution has been found in the given interval |
| Warning 308 | .IC or .NODESET name: This value does not match the value specified in the input signal. Zero-time value is: number |
| Warning 309 | .CHRSIM: The input signal will force the simulation to end at $\mathrm{V}=$ number |
| Warning 310 | .CHRSIM: The input signal will force the simulation to end at time = number |
| Warning 311 | .OPTION name: Ignored |
| Warning 312 | .OPTIMIZE name: Ignored |
| Warning 313 | .WIDTH name: Ignored |
| Warning 314 | .OPTFOUR: Obsolete statement ignored |
| Warning 315 | .GLOBAL: Nodes specified in this card are considered as global nodes from the introduction of the corresponding .GLOBAL card, NOT BEFORE |
| Warning 316 | .ENDS: The name does not match the .SUBCKT name |
| Warning 317 | name: Option unknown |
| Warning 318 | .RAMP name: Specification unknown. .RAMP ignored |
| Warning 319 | .PZ: Previous specification on name ignored |
| Warning 320 | .STEP: Previous card superseded |
| Warning 322 | .NOISE: Previous specification ignored |
| Warning 323 | .DC: Previous values superseded |
| Warning 324 | .RAMP: Previous values superseded |
| Warning 325 | .TRAN: Previous values superseded |
| Warning 326 | .OPTIMIZE/.EXTRACT: Node name is connected to ground |

Table A-12. Warnings Related to Commands

| Warning Number | Description |
| :---: | :---: |
| Warning 327 | .TRAN: The parameter TMAX is not used |
| Warning 328 | .AC: Previous values superseded |
| Warning 329 | .TRAN: Specification ignored |
| Warning 330 | .TRAN: UIC specification accepted |
| Warning 331 | .SENS: Element name not found |
| Warning 332 | .SENS: Node name not found |
| Warning 333 | .PZ: Node name not found |
| Warning 334 | .PZ: Element name not found |
| Warning 335 | .TF: Node name not found: .TF ignored |
| Warning 336 | .TF: Element name not found: .TF ignored |
| Warning 337 | .FIX: Element name not found |
| Warning 338 | .UNFIX: Element name not found |
| Warning 339 | .NOISE: Element/object name not found |
| Warning 340 | .MC: Element name not found |
| Warning 341 | .MC: Node name not found |
| Warning 342 | .STEP: Parameter name not found |
| Warning 343 | .STEP: No MOS name found |
| Warning 344 | .OPTFOUR: Voltage source name found |
| Warning 345 | .OPTFOUR: Node name found |
| Warning 346 | .PRINT or .PLOT: Node name undeclared |
| Warning 347 | .PRINT or .PLOT: Element name undeclared |
| Warning 348 | .DC: Unknown sweep source name |
| Warning 349 | .AC: No output specified in AC analysis: use .PLOT or .PRINT statement |
| Warning 350 | .MC: Specification ignored |
| Warning 351 | .OPTIMIZE: Ignored |
| Warning 352 | .NOISE: Must be used in AC analysis only. NOISE analysis omitted |
| Warning 353 | .IC: Node name not found |
| Warning 354 | .NODESET: Node name not found |
| Warning 355 | .GUESS: Node name not found |

Table A-12. Warnings Related to Commands

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 356 | .CONSO: Voltage source name not found |
| Warning 357 | . .PROBE: Too many nodes to display. This value can be overridden by .OPTION |
| LIMPROBE = value |  |

Table A-12. Warnings Related to Commands

| Warning Number | Description |
| :---: | :---: |
| Warning 382 | .OPTION name |
| Warning 392 | .STEP PARAM name: Sweep already defined in the .DC command |
| Warning 393 | .PROBE ISUB (name): No wild character allowed |
| Warning 394 | .PZ ignored because of FNZ functions |
| Warning 395 | .PROBE name: No nodes/objects found |
| Warning 396 | ISUB(name) not accessible: name is a global node |
| Warning 397 | ISUB: Node name not found |
| Warning 398 | .PROBE: Missing keyword AC, DC or TRAN |
| Warning 399 | Unable to display I(M/B/Jxx): name assumed |
| Warning 400 | .TRAN: TSTART > TSTOP: TSTART set to 0 |
| Warning 401 | .STEP: INCR_SPEC > T2-T1 |
| Warning 402 | .NOISE: zero or negative argument |
| Warning 403 | .AC: Frequency cannot be 0.0 or less: The value has been reset to 1.0 |
| Warning 404 | .MODDUP: element name not found |
| Warning 405 | .MODDUP: cannot be used on element name |
| Warning 406 | .LIB cannot find name |
| Warning 407 | .SETSOA ignoring SOA on model name |
| Warning 408 | .SETSOA ignoring SOA on object name |
| Warning 409 | .TF analysis not performed: Bad operating point |
| Warning 410 | The line is too long: It has been truncated |
| Warning 411 | .OPTNOISE: previous command superseded |
| Warning 412 | .OPTNOISE: ON/OFF expected: name found |
| Warning 413 | .MC: Unknown specification name: LOT or DEV expected |
| Warning 414 | .FOUR: Parameter TSTOP is ignored |
| Warning 415 | .TRAN: Parameter TPRINT is set to: name |
| Warning 416 | .OPTFOUR: Previous values superseded |
| Warning 417 | .USE: DC value for source name has been changed |
| Warning 418 | .GLOBAL: Some subcircuits are already defined, if these subcircuits make use of nodes which will appear in .GLOBAL statements, results can be in error |

Table A-12. Warnings Related to Commands

| Warning Number | Description |
| :---: | :---: |
| Warning 419 | .OPTFOUR: Using INTERPOLATE=0 may increase the number of points computed by the simulator |
| Warning 420 | Missing FPORT number name |
| Warning 421 | LOT/DEV specification on parameter name ignored |
| Warning 422 | .PZ: Specified device is not a 'voltage-like' element |
| Warning 423 | .OPTFOUR: TSTART > TSTOP: TSTART is ignored |
| Warning 424 | .OPTFOUR: TSTART < 0: TSTART is ignored |
| Warning 425 | .OPTFOUR: TSTOP < 0: TSTOP is ignored |
| Warning 426 | .OPTFOUR: NBPT < 0: NBPT is ignored |
| Warning 427 | .OPTFOUR: FS < 0: FS is ignored |
| Warning 428 | .OPTFOUR: Fnormal < 0: Fnormal is ignored |
| Warning 429 | .OPTFOUR: Fmin < 0: Fmin is ignored |
| Warning 430 | .OPTFOUR: Fmax < 0: Fmax is ignored |
| Warning 431 | .OPTFOUR: Fund < 0: Fund is ignored |
| Warning 432 | name: Only Magnitude or DB of NOISE outputs are available |
| Warning 433 | LOT/DEV specification is ignored on the non-primitive parameter name |
| Warning 434 | The given value for VSW0 is superior to VSW1:The values will be interchanged |
| Warning 435 | DEFAD/DEFAS/DEFPD/DEFPS overwritten by .OPTION XA for MOS models BERKELEY/BSIMxx/EKV and MM9 |
| Warning 436 | .EXTRACT: Unable to open file name |
| Warning 437 | .PLOT/.PRINT: wave name will be plotted as |
| Warning 438 | .TRAN: last Tstep ignored. |
| Warning 439 | .SETBUS: last Time point ignored |
| Warning 440 | name ignored with Eldo Mach |
| Warning 441 | .STEP: increment must be positive: name used |
| Warning 442 | .PARAM name |
| Warning 443 | .MEAS name |
| Warning 444 | .STEP: Compared to Eldo 5.4, the semantic of the .STEP ... LIN has changed: LIN stands for 'number of runs' <br> Rather use keyword INCR if 'increment value' is meant |

Table A-12. Warnings Related to Commands

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 445 | .TVINCLUDE: name |
| Warning 446 | .PLOT: name statement removed. It appears more than once. |
| Warning 447 | .STEP LIB: name |
| Warning 448 | .MPRUN name Ignored: Cannot distribute jobs (no multi-run analysis or no hosts) |
| Warning 449 | .NET name |
| Warning 450 | EXTRACT MODE: name |
| Warning 451 | Can't update correlation coefficient depending of parameter name |
| Warning 452 | .CORREL ignored, no statistical analysis found. |
| Warning 453 | .DSP name |
| Warning 454 | .PLOT: unexpected output name |
| Warning 455 | .PLOTBUS: limited to 53 bits: name not plotted |
| Warning 456 | .SIGBUS: Only first values specified for bus name will be taken for .SST analysis |
| Warning 457 | .STEP: no SST analysis found, keyword (AUTOINCR) ignored |
| Warning 458 | .MC: vary was already specified... |
| Warning 459 | .EXTRACT DC: DCTRAN assumed since both transient and ac analysis found in |
| the netlist |  |

## Warnings Related to Models

The following warning messages are preceded by MODEL <name>:
Table A-13. Warnings Related to Models

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 501 | No parameter specified. Default values are used |
| Warning 502 | GOFF less than zero |
| Warning 503 | Access resistors for this model are created as objects |
| Warning 504 | Unable to match reverse and forward region. BV = number |
| Warning 505 | Reset parameter |
| Warning 508 | LAMBDA value is high and may cause problems of convergence |
| Warning 509 | KB1 is set to number |

Table A-13. Warnings Related to Models

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 510 | Parameter XQC ignored |
| Warning 512 | IBV set to number milliAmps. IBV has been increased in order to create a <br> continuous diode current representation in the breakdown region. |
| Warning 513 | Parameter CF1 set to the default value: number |
| Warning 514 | Parameter CF3 set to the default value: number |
| Warning 515 | Parameters specific to BSIM appear and LEVEL is neither 8 or 11 |
| Warning 516 | LOT and DEV cannot be applied on R\|L|C parameters |
| Warning 517 | Parameter MJSW must be less than 1.0. Default is used |
| Warning 518 | Parameter MJ must be less than 1.0. Default is used |
| Warning 519 | LOT specification is less than or equal to zero |
| Warning 520 | DEV specification is less than or equal to zero |
| Warning 521 | The following parameter has an unusual value: |
| Warning 522 | DMUT parameter appears in a non-ST model |
| Warning 523 | SUBSN=1 is not allowed on a lateral PNP |
| Warning 524 | VTH1 > VTH2 |
| Warning 525 | VLO > VHI |
| Warning 526 | Model Warning |
| Warning 527 | Parameter AF has an unusual value |
| Warning 528 | Parameter KF has an unusual value |
| Warning 529 | Only one threshold is allowed for BIT A2D models: The average value has <br> been taken |
| Warning 530 | MCMOD cannot be applied on the model parameter: It can only be applied to a <br> nominal value: MCMOD ignored |
| Warning 531 | Sinwave function: Theta factor is negative |
| Warning 532 | COX is ignored because TOX is given |
| Warning 533 | The model parameters (DW/RSH) that are specific to RC WIRE have been |
| ignored |  |

Table A-13. Warnings Related to Models

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 537 | name, parameter ignored |

## Warnings Related to Subcircuits

The following warning messages are preceded by SUBCKT <name>:
Table A-14. Warnings Related to Subcircuits

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 701 | Unused parameter: name |
| Warning 702 | name: Cannot be updated with .LIB in interactive mode |
| Warning 703 | SUBCKT name cannot be that of a keyword |
| Warning 704 | This pin name appears more than once on definition |
| Warning 705 | The header of this SUBCKT contains node names defined as global |

## Miscellaneous Warnings

Table A-15. Miscellaneous Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 901 | Last time ignored on input signal at line: number |
| Warning 902 | name: Model parameter ignored |
| Warning 903 | Too many nodes to plot (>8) |
| Warning 904 | Previous value of name superseded |
| Warning 905 | VSAT is set to: number |
| Warning 906 | VSATM is set to: number |
| Warning 907 | Parameter not used: name |
| Warning 908 | name: This parameter cannot be assigned |
| Warning 909 | name: Unknown parameter |
| Warning 910 | Unable to measure ISUB(name): Multiple connections |
| Warning 911 | PORT name has only one connection |

Table A-15. Miscellaneous Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 912 | IBIS: name |
| Warning 913 | IBIS: parameter name ignored |
| Warning 914 | IBIS: parameter name not in the interval [0,1] is ignored |
| Warning 915 | Probably missing a path to ground from object name |
| Warning 916 | Unable to parse expression name |
| Warning 917 | SWEEP specification on TRAN/DC/AC ignored when .STEP are used: these <br> two syntaxes are not compatible |
| Warning 918 | The check for instance duplicates has been disabled (netlist too large). Use <br> .OPTION CHECKDUPL to override this limit. |
| Warning 919 | .OPTION ACCOUT=1 can not be applied to FOUR(name). |
| Warning 920 | Instances name, * not created because M is 0* |
| Warning 921 | MC variation on name |

Table A-16. Miscellaneous Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 1001 | .NOISETRAN ignored: Only single TRAN analysis is allowed |
| Warning 1002 | .NOISE ignored because the output node is not defined |
| Warning 1003 | .SWITCH: Element name not found |
| Warning 1004 | .MCMOD: Parameter name not known |
| Warning 1005 | .MCMOD: Element name not known |
| Warning 1006 | COMMAND name removed from the include file |
| Warning 1007 | .SAVE and .RESTART used on the same file: .SAVE ignored |
| Warning 1008 | COMMAND name found in include file |
| Warning 1009 | .OPTION: Incorrect range for name |
| Warning 1010 | .PRINT or .PLOT: AC-like output name for non-AC analysis |
| Warning 1011 | .PRINT or .PLOT: Unexpected AC output name |
| Warning 1012 | .PLOT element name is not declared |
| Warning 1013 | .PROBE/.SAVE element name is not declared |
| Warning 1014 | .VIEW element name is not declared |

Table A-16. Miscellaneous Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 1015 | Element name is not found |
| Warning 1016 | .SOLVE: Previous specifications superseded |
| Warning 1017 | AC input sources used in connection with FPORT |
| Warning 1018 | Digital gates are not handled in DCSWEEP |
| Warning 1019 | .WC and .MC cannot be used together: .WC ignored |
| Warning 1020 | .PZ analysis might give unexpected results because several AC sources are |
| found in the circuit |  |

Table A-16. Miscellaneous Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 1041 | COMMAND .PRINT or .PLOT SSTJITTER: Expected SSTJTTER output, <br> and not name |
| Warning 1042 | COMMAND .PRINT or .PLOT SSTSTABIL: Expected SSTSTABIL output, <br> and not name |
| Warning 1043 | COMMAND .PRINT or .PLOT: output name will be written as real/imaginary <br> parts in files which do not support complex format. |
| Warning 1044 | COMMAND .EXTRACT or .MEAS: Unexpected name output |
| Warning 1045 | COMMAND .PRINTFILE: Element name not declared |
| Warning 1046 | COMMAND .DSPF_INCLUDE: file name. An extra X has been added on <br> name. That rule of adding an extra X will now be used by default in that file <br> for all subsequent *\|NET instructions. |
| Warning 1047 | BUS name is of size 0: Could be declaration of that bus is missing. |
| Warning 1048 | .OPTION name: list of values are limited to 10 elements. <br> Warning 1049COMMAND .OPTWIND name is incompatible with options defined as a list <br> of values. Only first value is kept. |
| Warning 1050 | COMMAND name:Node name not found |
| Warning 1051 | COMMAND name:Device name not found |
| Warning 1052 | Object name: Eldo will simulate as if CTYPE = 1 had been set on that <br> instance... This is because C value seems not to be dependant on the pin bias, <br> or pins are connected to power supply or ground, and in such situations, <br> CTYPE = mode is usually more appropriate.. However, in case this tuning is <br> here not appropriate, just set CTYPE = on the device, or use .OPTION <br> NOAUTOCTYPE in order to disable this setup. |
| Warning 1056 | COMMAND .MC: Several .MC commands found in the netlist. Only last one <br> will be used. <br> Warning 1053 |
| COMMAND .EXTRACT: name is ignored. |  |
| Warning 1054 | COMMAND .FOUR: name removed |
| Warning 1055 | COMMAND .MC: incorrect value for PRINT_EXTRACT. name found while <br> Warng 1058 |
| COMMAND .PUNCH: unimplemented analyze type (name) requested. <br> Command ignored |  |
| COMMAND name: SNF output required but no .SNF card has been given |  |
| with method |  |

Table A-16. Miscellaneous Warnings

| Warning Number | Description |
| :---: | :---: |
| Warning 1060 | D2A/A2D command ignored using ADMS. |
| Warning 1061 | The SUBCKT(S) listed above will not be changed by the STEP command, they will remain the same for the entire stepping process. Therefore, results might not be as expected... Suggest to use .ALTER command in .cir file instead. |
| Warning 1062 | COMMAND .AGE: TSTART/TSTOP specifications are ignored because of TWINDOW. |
| Warning 1063 | COMMAND .EXTRACT/.MEAS name: Unable to find any .DATA associated with current analysis. Command ignored. |
| Warning 1064 | COMMAND .EXTRACT/.MEAS name: Unable to find an item named name in .DATA name. Command ignored. |
| Warning 1065 | COMMAND .EXTRACT/.MEAS name: Complex measurements are not compatible with optimization. Command ignored. |
| Warning 1066 | COMMAND .EXTRACT/.MEAS name: Unable to find a .DATA named name. Command ignored. |
| Warning 1067 | COMMAND .EXTRACT/MEAS name: in name some points are outside the simulation interval. They will be ignored by the fitting command. |
| Warning 1068 | COMMAND .EXTRACT/MEAS name: in name some points are not correctly ordered, or not unique for a given X value. Fitting command ignored. |
| Warning 1069 | COMMAND .EXTRACT/.MEAS name: in name some points can't be simulated. Fitting command ignored. |
| Warning 1070 | COMMAND .PLOT/.PRINT/.PROBE: wave name contains some errors. This command is ignored. |
| Warning 1071 | COMMAND .PLOT/.PRINT/.PROBE: Unexpected character 'name' found |
| Warning 1072 | COMMAND .PRINTFILE: xaxis START value for file name has been set to: |
| Warning 1073 | COMMAND .PRINTFILE: xaxis STOP value for file name has been set to: |
| Warning 1074 | In corner name of library name .BIND commands can't be processed by the STEP command.They will be ignored during the stepping process, therefore results might not be as expected. Suggest to use .ALTER command instead. |
| Warning 1075 | COMMAND .RAMP: syntax error in command declaration: |
| Warning 1076 | dc voltage reset to initial transient source value for source name |
| Warning 1077 | COMMAND .PLOTBUS: incorrect BASE value: name. Default value will be used. |
| Warning 1078 | COMMAND .PLOTBUS: BIN, DEC, OCT or HEX is expected after keyword BASE. Default value will be used. |

Table A-16. Miscellaneous Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 1079 | COMMAND .PLOTBUS: UNSIGNED or 2COMP is expected after keyword <br> RADIX. Default value will be used. |
| Warning 1080 | COMMAND .PLOTBUS: display keywords BASE and RADIX are mutually <br> exclusive. Priority is given to RADIX. |
| Warning 1081 | COMMAND .PLOTBUS: display keywords BASE and RADIX are ignored. <br> They do not apply on analog buses. |
| Warning 1082 | COMMAND .USE_TCL: NATIVE_TCL or EZWAVE_UDF is expected <br> after keyword MODE. Default value will be used. |
| Warning 1083 | COMMAND .TRAN is ignored when .MODSST is set. |
| Warning 1084 | COMMAND .OBJECTIVE: unsupported analysis: name. |
| Warning 1085 | COMMAND .PRINTFILE: file name cannot support more than name <br> analysis. |
| Warning 1087 | COMMAND .SIGBUS: Last value for bus name is not consistent with <br> periodic definition. It should be equal to first value. |
| COMMAND .OPTION: name has been deprecated and will be removed from |  |
| future releases. |  |

Table A-16. Miscellaneous Warnings

| Warning <br> Number | Description |
| :--- | :--- |
| Warning 1099 | COMMAND .FOUR: name removed. Device name is unknown. |

## Appendix B Troubleshooting

## Introduction

Most users of any product will from time to time experience problems in its use. This appendix is intended to provide an easy to use quick reference from which such problems can be identified and corrected.

## Common Netlist Errors

Below is a list of the common errors to look out for when producing an input netlist:

- First Line of a File Not the Title

The first line of a netlist must be the title of the circuit. If part of the circuit description is found on the first line, it will be ignored. If the first line is a blank, this will be taken as the title line.

- Correct Usage of the Simulator Accuracy (eps, vntol, reltol)

The simulator accuracy parameters are the most important Eldo parameters-they must be correctly initialized.

## 1

For more details refer to the Speed and Accuracy chapter.

- Correct Units on Devices

It is very important to make sure that all the components in the netlist have correct units; one mistake can have a large effect. An example of this is specifying units of farads instead of picofarads.

- Missing Model

Make sure that model definitions are available to the simulator, either directly in the netlist, or in a referenced library.

- Missing Voltage Sources

Independent voltage sources defined to have a voltage of 0 V may be removed by Eldo in order to simplify calculations. If you wish to use a voltage source as a current probe, avoid defining its voltage as 0 V , but instead, define its voltage value to be very small. Moreover, currents through components may be measured directly, therefore, the use of voltage sources as current probes is not necessary.

- Correct Model Name Syntax

The first character of a model name cannot be a number. This causes the compilation of the netlist to be interrupted, and an error message to be displayed.

- Unknown Model Parameter

When defining model parameter values, care must be taken to ensure that the parameter is spelt correctly and that it is indeed a legal parameter of the device.

- Ground (0) Node

A 0 node (i.e. ground) must always be present in the input netlist.
Note
Eldo does not recognize GND as GROUND!

- Reserved Keywords

Some keywords should not be specified in a .PARAM command. If they are then errors will be generated. See Table 10-21 and Table 10-22 on page 779.

## Appendix C Examples

## Introduction

This chapter contains the set of examples that are distributed with the Eldo software package. Each example consists of the complete Eldo netlist of the circuit, together with output results obtained from EZwave, the Eldo waveform viewer. A summary of the examples is shown below. Listings for these examples may be found in the following subdirectories included with your software:

```
$MGC_AMS_HOME/examples/eldo/
```

where \$MGC_AMS_HOME is the directory where the software resides.
Note
For more examples please refer to "Examples for IEM" on page 1102 and the Tutorials chapter.

Table C-1. Eldo Examples

| Example | Circuit Name |
| :--- | :--- |
| Example\#1—SC Schmitt Trigger | trigger.cir |
| Example\#2—4-bit Adder | ad4b.cir |
| Example\#3—CMOS Op-amp (Open Loop) | aopalt.cir |
| Example\#4—CMOS Op-amp (Closed Loop) | aopbou.cir |
| Example\#5—5th Order Elliptic SC Low Pass Filter | ellipt5.cir |
| Example\#6—Charge Control in MOS 4 and 6 | niv4_6.cir |
| Example\#7—Active RC Band Pass Filter | ua741.cir |
| Example\#8—2nd Order Delta Sigma Modulator | integrator.cir |
| Example\#9—Operational Amplifier | extract.cir |

## Example\#1—SC Schmitt Trigger

This example deals with a transient analysis of an SC Schmitt trigger circuit. The complete netlist can be found in the file trigger.cir.

## Complete Netlist

```
Schmitt trigger
.model ampop opa level=2 voff=0 sl=50e06
+ cin=0 rs=10 vsat=5 gain=5000 fc=5000
.subckt ampli 1 2 3
opa1 2 1 3 0 ampop
.ends ampli
s1 cl 1 2 1k
s2 cl 3 6 1k
s3 clb 6 8 1k
s4 clb 9 4 1k
s5 cl 9 0 1k
c1 2 0 0.01n
c2 3 0 0.01n
c3 6 8 0.01n
c4 8 9 0.001n
x1 2 3 4 ampli
x2 8 0 6 ampli
.chrent cl 0 -5 0.1u 5 4.9u 5 5u -5 10u -5 p
.chrent clb 0 -5 5u -5 5.1u 5 9.9u 5 10u -5 p
.chrent 1 0 -2 0.2m 2 0.4m -2 f
.tran 1u 0.4m uic
.plot tran v(1) v(4) (-6,6)
.print tran v(1) v(4)
.option eps=1e-4
.end
```


## Simulation Results

Figure C-1. Example\#1—Simulation Results


## Example\#2—4-bit Adder

This example deals with a transient analysis of a 4-bit adder. The complete netlist can be found in the file ad4b.cir.

## Complete Netlist

```
ad4b
.model mod1 nmos
+ niv=6 eox=25.0N muo=600 nb=2.0e+16 dphif=0.6 vl=2.0e5
+ kw=2.24U kl=2.24U gw=3.91U gl=0.7U dinf=0.1 ve=10.0e+4
+ ldif=10U cdifs0=0.0001 cdifp0=0 dw=0 dl=0.8u rec=0.15u
+ vt0=0.55 kb=0.1 tg=0.06
```

```
.model mod2 pmos
+ niv=6 eox=25n muo=225 nb=2.0e+16 dphif=0.7 vl=1.9e+5
\(+\mathbf{k w}=0.52 \mathrm{u} \mathbf{k l}=4 \mathrm{u} \mathbf{g w}=0.453 \mathrm{u} \mathbf{g l}=0.7 \mathrm{u}\) dinf \(=0.17\) ve=7.35e+4
+ ldif=10u cdifs0=0.000316 cdifp0=0 dw=0 dl=1.5u
+ rec \(=0.5 \mathrm{u}\) vt \(0=0.55 \mathrm{~kb}=0.34 \mathrm{tg}=0.14\)
.model mod3 nmos
+ niv=6 dw=0.5u dl=1.1u eox=60n dphif=0.7 vt0=-4.0 muo=446.0
\(+\mathbf{k b}=0.4 \mathbf{k w}=0.0 \mathrm{u} \mathbf{k l}=0.0 \mathrm{u} \mathbf{g w}=2.4 \mathrm{u} \mathrm{gl}=0.5 \mathrm{u} \operatorname{dinf}=0.14\) ve=12. \(8 \mathrm{e}+4\)
\(+\mathbf{r e c}=0.4 \mathrm{u}\) tg=0.05 vl=1.0e+5 sh=0.1 nb=1e+15
.model mod4 nmos
+ niv=6 dw=0.5u dl=1.1u eox=60.0n dphif=0.7 vt0=0.7 muo=672.0
\(+\mathbf{k b}=0.234 \mathbf{k w}=2.17 \mathrm{u} \mathbf{k l}=0.49 \mathrm{u} \mathbf{g w}=4.325 \mathrm{u} \mathbf{g l}=0.872 \mathrm{u}\) dinf=0.105
\(+\mathbf{v e}=7.71 \mathrm{e}+4 \mathrm{rec}=0.4 \mathrm{u} \mathbf{t g}=0.05 \mathrm{vl}=8.55 \mathrm{e}+4 \mathbf{s h}=0.1 \mathbf{n b}=1.0 \mathrm{e}+15\)
*subcircuit definition
.subckt flipflop vdd vss h d q qb
m1 n1 n2 \(0 \quad\) vss \(\bmod 4 \mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m2 n2 n1 0 vss mod4 \(\mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m3 n2 \(h \quad 0 \quad\) vss mod4 \(w=15 u \quad l=3.5 u\)
m4 n4 n2 \(0 \quad\) vss mod4 \(w=15 u \quad \mathbf{l}=3.5 u\)
m5 n1 n5 \(0 \quad\) vss \(\bmod 4 \mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m6 \(n 4 \quad h \quad 0 \quad\) vss mod4 \(\mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m7 n4 n5 0 vss mod4 \(\mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m8 n5 n4 \(0 \quad\) vss \(\bmod 4 \quad w=15 u \quad \mathbf{l}=3.5 u\)
m9 n5 d \(0 \quad\) vss mod4 \(\mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m10 q n2 0 vss mod4 \(\mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m11 q qb \(0 \quad\) vss mod4 \(\mathbf{w}=15 u \quad \mathbf{l}=3.5 u\)
m12 qb q 0 vss mod4 w=15u l=3.5u
m13 qb n4 0 vss mod4 w=15u \(\mathbf{l}=3.5 u\)
m14 vdd n1 n1 vss mod3 \(\mathbf{w}=6.0 u \quad \mathbf{l}=5.0 u\)
m15 vdd n2 n2 vss mod3 \(\mathbf{w}=6.0 \mathrm{u} \mathbf{l}=5.0 \mathrm{u}\)
m16 vdd n4 n4 vss mod3 w=6.0u l=5.0u
m17 vdd n5 n5 vss mod3 w=6.0u \(\mathbf{l}=5.0 \mathrm{u}\)
m18 vdd \(q\) q vss mod3 \(\mathbf{w}=6.0 u \mathbf{l}=5.0 u\)
m19 vdd qb vss mod3 w=6.0u l=5.0u
c1 n1 00.029 p
c2 n2 00.048 p
c3 n4 00.044 p
c4 n5 00.046 p
c5 q \(00.066 p\)
c6 qb \(00.053 p\)
.ends flipflop
*subcircuit definition
.subckt adder vdd vss a b er s sr
m1 n12 b a vss mod4 \(\mathbf{w}=4.0 \mathrm{u} \quad \mathbf{l}=4.0 \mathrm{u}\)
m2 \(\mathrm{s} \quad \mathrm{n} 13 \mathrm{n} 14\) vss \(\bmod 4 \mathbf{w}=4.0 \mathrm{u} \quad \mathbf{l}=4\).0u
m3 \(s\) er \(n 12\) vss mod4 \(\mathbf{w}=4.0 u \quad \mathbf{l}=4.0 u\)
m4 n12 n16 n11 vss mod4 \(\mathbf{w = 4 . 0 u} \quad \mathbf{l}=4.0 \mathrm{u}\)
m5 n11 a \(0 \quad\) vss mod4 \(\mathbf{w}=15.0 u \quad \mathbf{l}=3.5 u\)
m6 n16 b \(0 \quad\) vss \(\bmod 4 \quad \mathbf{w}=15.0 u \quad \mathbf{l}=3.5 \mathrm{u}\)
m7 n14 n12 \(0 \quad\) vss \(\bmod 4 \quad \mathbf{w}=15.0 u \quad \mathbf{l}=3.5 u\)
m8 n13 er \(0 \quad\) vss mod4 \(\mathbf{w}=15.0 u \mathbf{l}=3.5 u\)
m9 n17 b \(0 \quad\) vss mod4 w=15.0u \(\mathbf{l}=3.5 \mathrm{u}\)
m10 n17 a \(0 \quad\) vss \(\bmod 4 w=15.0 u \quad \mathbf{l}=3.5 u\)
```



## Simulation Results

Figure C-2. Example\#2—Simulation Results-1


Figure C-3. Example\#2—Simulation Results-2


## Example\#3-CMOS Op-amp (Open Loop)

This example deals with an AC analysis of an open loop CMOS operational amplifier circuit. The complete netlist can be found in the file aopalt.cir.

## Complete Netlist

```
aopalt
    .model mod1 nmos level=merck2 eox=25.0n mu0=600 nb=2.0e+16
+ dphif=0.6 vl=2.0e+5 kw=2.24u kl=2.24u lot=0.5% gw=3.91u gl=0.7u
+ dev=0.07e-6 dinf=0.1
+ ve=10.0e+4 ldif=10u cdifs0=0.0001 cdifp0=0.0
+ dw=0.0 dl=0.8u rec=0.15u vt0=0.55 kb=0.1 tg=0.06
.model mod2 pmos level=merck2 eox=25n mu0=225 nb=2.0e+16
+ dphif=0.7 vl=1.9e+5 kw=0.52u kl=4u gw=0.453u gl=0.7u dinf=0.17
+ ve=7.35e+4 ldif=10u cdifs0=0.000316 cdifp0=0
+ dw=0 dl=1.5u rec=0.5u vt0=-0.55 kb=0.34 tg=0.14
*amplifier
```

```
m1 a g vdd vdd mod2 w=120u l=5.5u
m2 b g vdd vdd mod2 w=120u l=5.5u
m3 d k a vodd mod2 w=116u l=3.5u
m4 s k b vdd mod2 w=116u l=3.5u
m5 c i vss vss mod1 w=63u l=6u
m6 a ep c vss mod1 w=130u l=4u
m7 b en c vss mod1 w=130u l=4u
m8 d d ff vss mod1 w=5.5u l=4.5u
m9 s d e vss mod1 w=5.5u l=4.5u
m10 ff e vss vss modl w=42u l=4u
m11 e e vss vss modl w=42u l=4u
m12 g g vdd vdd mod2 w=14.5u l=5.5u
m13 g g h vss mod1 w=9u l=5.5u
m14 i i h vdd mod2 w=19u l=4.5u
m15 i i vss vss modl w=6u l=6u
m16 j g vdd vdd mod2 w=20u l=5.5u
m17 j j k vss mod1 w=26u l=3.5u
m18 nl i k vdd mod2 w=3u l=3.5u
m19 nl nl vss vss modl w=4u l=3.5u
c1 s 0 1.5p
v1 vdd 0 3
v2 vss 0 -3
vinm en 0 0
vinp ep 0 ac
.mc 7 vdb(s)
.ac dec 10 1.0e3 1.0e9
.plot ac vdb(s)
.plot ac vp(s)
.option eps=1.0e-4
.end
```


## Simulation Results

Figure C-4. Example\#3—Simulation Results


## Example\#4—CMOS Op-amp (Closed Loop)

The circuit in this example is the same as in the last one with the exception being that the circuit is in a closed loop configuration. A transient analysis is performed and the complete netlist can be found in the file aopbou.cir.

## Complete Netlist

```
aopbau
.model mod1 nmos level=merck2 eox=25.0n mu0=600 nb=2.0e+16
+ dphif=0.6 vl=2.0e+5 kw=2.24u kl=2.24u gw=3.91u gl=0.7u dinf=0.1
+ ve=10.0e+4 ldif=10u cdifs0=0.0001 cdifp0=0.0
+ dw=0.0 dl=0.8u rec=0.15u vt0=0.55 kb=0.1 tg=0.06
.model mod2 pmos level=merck2 eox=25n mu0=225 nb=2.0e+16
```

```
+ dphif=0.7 vl=1.9e+5 kw=0.52u kl=4u gw=0.453u gl=0.7u dinf=0.17
+ ve=7.35e+4 ldif=10u cdifs0=0.000316 cdifp0=0
+ dw=0 dl=1.5u rec=0.5u vt0=-0.55 kb=0.34 tg=0.14
*amplifier
m1 a g vdd vdd mod2 w=120u l=5.5u
m2 b g vdd vdd mod2 w=120u l=5.5u
m3 d k a vodd mod2 w=116u l=3.5u
m4 s k b vdd mod2 w=116u l=3.5u
m5 c i vss vss mod1 w=63u l=6u
m6 a ep c vss mod1 w=130u l=4u
m7 b s c vss mod1 w=130u l=4u
m8 d d ff vss mod1 w=5.5u l=4.5u
m9 s d e vss mod1 w=5.5u l=4.5u
m10 ff e vss vss modl w=42u l=4u
m11 e e vss vss modl w=42u l=4u
m12 g g vdd vdd mod2 w=14.5u l=5.5u
m13 g g h vss modl w=9u l=5.5u
m14 i i h vdd mod2 w=19u l=4.5u
m15 i i vss vSs modl w=6u l=6u
m16 j g vdd vdd mod2 w=20u l=5.5u
m17 j j k vss mod1 w=26u l=3.5u
m18 nl i k vdd mod2 w=3u l=3.5u
m19 nl nl vss vss modl w=4u l=3.5u
c1 s 0 1.5p
v1 vdd 0 3
v2 vss 0 -3
v3 ep 0 pwl(0n 0 18n 0 19n 1 59n 1 60n 0)
.tran 1n 100n
.options eps=1.0e-6
.plot tran v(ep) v(s) (-0.3,1.2)
.end
```


## Simulation Results

Figure C-5. Example\#4—Simulation Results


## Example\#5—5th Order Elliptic SC Low Pass Filter

This example deals with a transient analysis on a 5th order SC low pass filter This type of circuit is used in those applications requiring the analysis of sampled data in analog circuits, being used in certain ADC/DAC and switch capacitor filters designs. The complete netlist can be found in the file ellipt5.cir.

## Complete Netlist

```
ellipt5
.model ampop opa level=2 voff=0 sl=50e06 cin=0p
+ rs=1 vsat=5 gain=10000 fc=5e3 cmrr=0
```

```
opa1 0 n5 n6 0 ampop
opa2 0 n10 n11 0 ampop
opa3 0 n15 n16 0 ampop
opa4 0 n21 n20 0 ampop
opa5 0 n25 s 0 ampop
sint1 ph1 e n1 1.0k 0.0p
sint2 ph1 n11 n3 1.0k 0.0p
sint3 ph1 n4 n6 1.0k 0.0p
sint4 ph1 n2 n5 1.0k 0.0p
sint5 ph1 n6 n7 1.0k 0.0p
sint6 ph1 n16 n9 1.0k 0.0p
sint7 ph1 n8 0 1.0k 0.0p
sint8 ph1 n11 n12 1.0k 0.0p
sint9 ph1 n20 n13 1.0k 0.0p
sint10 ph1 n14 n15 1.0k 0.0p
sint11 ph1 n16 n17 1.0k 0.0p
sint12 ph1 s n18 1.0k 0.0p
sint13 ph1 n19 0 1.0k 0.0p
sint14 ph1 n20 n22 1.0k 0.0p
sint15 ph1 S n23 1.0k 0.0p
sint16 ph1 n24 n25 1.0k 0.0p
sint17 ph2 n1 0 1.0k 0.0p
sint18 ph2 n3 0 1.0k 0.0p
sint19 ph2 n4 0 1.0k 0.0p
sint20 ph2 n2 0 1.0k 0.0p
sint21 ph2 n7 0 1.0k 0.0p
sint22 ph2 n9 0 1.0k 0.0p
sint23 ph2 n8 n10 1.0k 0.0p
sint24 ph2 n12 0 1.0k 0.0p
sint25 ph2 n13 0 1.0k 0.0p
sint26 ph2 n14 0 1.0k 0.0p
sint27 ph2 n17 0 1.0k 0.0p
sint28 ph2 n18 0 1.0k 0.0p
sint29 ph2 n19 n21 1.0k 0.0p
sint30 ph2 n22 0 1.0k 0.0p
sint31 ph2 n23 0 1.0k 0.0p
sint32 ph2 n24 0 1.0k 0.0p
```

```
c1 n6 n5 1.50536963p
c2 n6 n15 0.2589059p
c3 n4 n2 1.0p
c4 n3 n2 1.0p
c5 n1 n2 1.0p
c6 n10 n11 0.96577222p
c7 n7 n8 1.0p
c8 n9 n8 1.0p
c9 n16 n15 2.3362151p
c10 n16 n5 0.2589059p
c11 n16 n25 0.94246071p
c12 n13 n14 1.0p
c13 n12 n14 1.0p
c14 n20 n21 0.51354696p
c15 n18 n19 1.0p
c16 n17 n19 1.0p
c17 s n25 0.75440758p
c18 s n15 0.94246071p
c19 n22 n24 1.0p
c20 n23 n24 1.0p
.chrent e On 4 700n 4 800n 0 f
.chrent phi 0.0n -5.0 10.0n 5.0 490.0n 5.0
+ 500.0n -5.0 1000.0n -5 p
.chrent ph2 0.0n -5.0 500.0n -5.0 510.0n 5.0
+ 990.0n 5.0 +1000.0n -5 p
.plot tran v(s) (-0.8, 0.4)
.plot tran v(n6) (-1.8, 0.4)
.plot tran v(n11) (-1.5, 1.0)
.plot tran v(n16) (-0.4, 1.0)
.plot tran v(n20) (-0.8, 1.2)
.tran 1u 50u uic
.option eps=1e-4 hmin=5n
.end
```


## Simulation Results

Figure C-6. Example\#5—Simulation Results


## Example\#6-Charge Control in MOS 4 and 6

This example deals with the transient analysis of a MOS circuit containing both MOS level 4 and 6 models, illustrating the differences in model performance. The complete netlist can be found in the file niv4_6.cir.

## Complete Netlist

```
niv4_6
    .model m4 nmos level=4 vtO=1.2v eox=25n uo=600
+ nsub=2.0e16 phi=0.6 vmax=2.0e5 kw=2.24u kl=2.24u
+ gw=3.91u gl=0.7u dinf=0.1 kb=0.1 ve=1.0e4
+ ldif=10u cj=0.0001 cjsw=0 dw=0 dl=0.8u rec=0.15u
+ tg=0.06
```

```
.model m2 nmos level=6 vt0=1.1v eox=25n uo=600
+ nsub=2.0e16 phi=0.6 vmax=2.0e5 kw=2.24u kl=2.24u
+ gw=3.91u gl=0.7u dinf=0.1 kb=0.1 ve=1.0e4
+ ldif=10u cj=0.0001 cjsw=0 dw=0 dl=0.8u rec=0.15u
+ tg=0.06
m1 1 2 1 bulk m4 w=10u l=3u
c1 1 0 0.05pf
m2 3 2 3 bulk m2 w=10u l=3u
c2 3 0 0.05pf
vb bulk 0 0
vin 2 0 pulse (0 5 10n 1n 1n 18n 30n)
.tran 1ns 160ns uic
.print tran v(1) v(2) v(3)
.plot tran v(1) (0, 2)
.plot tran v(2) (0, 6)
.plot tran v(3) (0, 3)
.option eps=1.0e-6
.end
```

In the simulation below, $\mathrm{V}(1)$ is the result of the charge control model and $\mathrm{V}(3)$ is the result of the capacitive model. For $\mathrm{V}(3)$ the error on the charge is accumulated and error is increasing at each period. However, for $\mathrm{V}(1)$ there is no error on the charges.

## Simulation Results

Figure C-7. Example\#6—Simulation Results


## Example\#7-Active RC Band Pass Filter

This example deals with the AC analysis of an active RC band pass filter circuit containing a UA741 operational amplifier. The complete netlist can be found in the file ua741.cir.

## Complete Netlist

```
ua741
* .MODEL definitions
.model npn npn bf=160 rb=100 cjs=2p tf=0.3n
+ tr=6n cje=3p cjc=2p vaf=100
.model npq npn bf=160 rb=100 cjs=2p tf=0.3n
+ tr=6n cje=3p cjc=2p vaf=100 is=2p
.model pnp pnp bf=20 rb=20 tf=1n tr=20n
+ cje=6p cjc}=4p vaf=10
```

```
.model pnq pnp bf=20 rb=20 tf=1n tr=20n
+ cje=6p cjc=4p vaf=100 is=2p
*subcircuit ua741
.subckt ua741 2 3 6 4 7
r1 1 4 1k
r2 15 4 50k
r3 5 4 1k
r4 17 4 5k
r5 18 16 39k
r6 22 23 4.5k
r7 20 23 7.5k
r8 21 4 50k
r9 19 4 50
r10 24 6 25
r11 6 25 50
cx 22 14 30p
q1 9 3 10 npn
q2 12 13 10 pnp
q3 9 2 11 npn
q4 14 13 11 pnp
q5 12 15 1 npn
q6 14 15 5 npn
q7 7 12 15 npn
q8 9 9 7 pnp
q9 13 9 7 pnp
q10 13 16 17 npn
q11 16 16 4 npn
q12 18 18 7 pnp
q13 14 19 4 npn
q14 20 14 21 npn
q15 22 18 7 pnp
q16 22 23 20 npn
q17 20 21 19 npn
q18 22 24 6 npn
q19 7 22 24 npq
q20 4 20 25 pnq
q21 6 6 23 npn
.ends
r1 1 3 12.952k
r22 3 0 846.01
r2 4 5 322.2k
c1 3 5 100n
c2 3 4 100n
x1 4 0 5 40 70 ua741
r3 5 6 150k
r4 6 7 293.8k
r5 7 8 15k
r6 8 9 15k
r7 9 10 15k
r8 11 6 14.05k
c3 6 7 100n
c4 10 11 100n
```

```
x2 6 0 7 40 70 ua741
x3 8 0 9 40 70 ua741
x4 10 0 11 40 70 ua741
r9 9 12 47k
r10 12 13 365.6k
r11 13 14 15k
r12 14 2 15k
r13 2 15 15k
r14 16 12 20.71k
c5 12 13 100n
c6 15 16 100n
x5 12 0 13 40 70 ua741
x6 14 0 2 40 70 ua741
x7 15 0 16 40 70 ua741
vee 40 0 dc -15
vcc 70 0 dc 15
v0 1 0 ac 1
.ac dec 100 10 1000
.plot ac vdb(2) vdb(9) vdb(5) (-100, 100)
.plot ac vp(2) vp(9) vp(5) (180, -180)
.end
```


## Simulation Results

Figure C-8. Example\#7—Simulation Results


## Example\#8—2nd Order Delta Sigma Modulator

This example deals with the transient analysis of a second order delta sigma modulator circuit. The complete netlist can be found in the file integrator.cir.

## Complete Netlist



```
s5 phi inm 3 switch
s6 phib 3 0 switch
c2 3 4 2p
s7 phi 4 0 switch
s8 phib 4 em switch
s10 phi ref 5 switch
sl1 phib ref 6 switch
sl2 phib 5 0 switch
s13 phi 6 0 switch
c3 5 7 2p
c4 6 8 2p
s14 phi 7 0 switch
s15 phi 8 0 switch
s16 phib 7 9 switch
s17 phib 8 10 switch
s18 comp 9 em switch
s19 compb 9 ep switch
s20 comp 10 ep switch
s21 compb 10 em switch
c5 ep sm 6p
c6 em sp 6p
eopal sm sp ep em -1meg
**** integrator 2 ****************
sil phi sm il switch
si2 phib il 0 switch
cil i1 i2 2p
si3 phib i2 0 switch
si4 phi i2 iep switch
si5 phi sp i3 switch
si6 phib i3 0 switch
ci2 i3 i4 2p
si7 phib i4 0 switch
si8 phi i4 iem switch
sil0 phi ref i5 switch
si11 phib ref i6 switch
si12 phib i5 0 switch
si13 phi i6 0 switch
ci3 i5 i7 2p
ci4 i6 i8 2p
si14 phib i7 0 switch
si15 phib i8 0 switch
si16 phi i7 i9 switch
si17 phi i8 ilO switch
si18 comp i9 iem switch
si19 compb i9 iep switch
si20 comp i10 iep switch
si21 compb i10 iem switch
ci5 iep ism 6p
ci6 iem isp 6p
eopa2 ism isp iep iem -1meg
vref ref 0 -1
***** comparator ********
compdiff ism isp voutp voutn vhi=2.5 vlo=-2.5 tcom=0.0n
+ tpd=0.0n
```

```
***** latch **************
sl1 phi voutn memn switch
sl2 phi voutp memp switch
nandl memp qu qubar vhi=2.5 vlo=-2.5 tpd=0.0n
+ vthi=0.1 vtlo=-0.1
nand2 memn qubar qu vhi=2.5 vlo=-2.5 tpd=0.0n
+ vthi=0.1 vtlo=-0.1
***** delay **************
delayn qubar compb 81.3802n
delayp qu comp 81.3802n
***** voltage source input **************
vin1 inp 0 sin(0 0.5 12.288k 0 0)
vin2 inm 0 sin(0 -0.5 12.288k 0 0)
.chrent phib 0 -5 41.6901n -5 42.6901n 5 79.3802n 5
+ 80.3802n -5 81.3802n -5 P
.chrent phi 0 5 40.6901n 5 41.6901n -5
+ 80.3802n -5 81.3802n 5 P
.tran 81.3802n 81.3802us
.option eps=1.0e-9 step=5.0862625n be
.plot tran v(inp,inm) (-1,1)
.plot tran v(sm,sp) (-3.0,3.0)
.plot tran v(isp,ism) (-3.5,3.5)
.plot tran v(comp) (-3.0,3.0)
. end
```


## Simulation Results

Figure C-9. Example\#8—Simulation Results


## Example\#9—Operational Amplifier

This example deals with the transient analysis of an operational amplifier circuit. In addition, the slew rate and circuit settling time with a 5\% error band are calculated and written to the ASCII output file. The complete netlist can be found in the file extract.cir.

## Complete Netlist

```
OPERATIONAL AMPLIFIER
.model bu opa level=2 sl=1e6
c1 out 0 10u
opal nonin in out 0 bu
rf in out 2.5k
ri 0 in 0.625k
v1 nonin 0
+ pwl (0.0 -0.1 0.1u 0.1 250u 0.1 260u -0.1 500u -0.1)
```

```
.tran 100u 500u
.option vntol=1e-8 reltol=1e-8 hmax=1u eps=1e-8
.plot tran v(out)
.defmac sett(x,y,tix,limit)=
+ (xycond(x, (y > (yval(y,tix)*(1.0+limit))) ||
+ (y < (yval(y,tix)*(1.0-limit))),tix,0.0))
.defmac slewrate(a)=
+ ((slope(a,yval (a,0.0) +(max(a) -yval (a,0.0))/3.0)+
+ slope(a,yval(a,0.0)+(max(a)-yval(a,0.0))*2.0/3.0))/2.0)
.extract $sett(xaxis,v(out),200e-6,0.05)
.extract $slewrate(v(out))
.end
```


## Simulation Results-1

Figure C-10. Example\#9-Simulation Results-1


## Simulation Results-2 (Zoom)

Figure C-11. Example\#9—Simulation Results-2 (Zoom)


## Appendix D Eldo Interactive Mode

## Introduction

Eldo Interactive is a way of invoking Eldo and sending commands to it interactively instead of sending the commands in the netlist. Some other AMS tools, such as ICanalyst, make use of Eldo in the interactive mode, although this is all transparent to the user. Eldo Interactive Mode is not supported by Questa ADMS.

To invoke Eldo in the interactive mode, type:

```
eldo cir_file_name -inter
```

where cir_file_name is the name of the .cir control file to be simulated. Default extension is .cir.

When working in Eldo interactive mode, a prompt will appear:

```
eldo>
```

There is some help information available: you can type help at the eldo> prompt and you will see the list of available commands; type help <command_name> for more information about a particular command, or type help all to obtain the complete help listing.

When working in Eldo interactive mode, you can type your command after the eldo> prompt. For continuation lines, you must type the backslash character $(\backslash)$ at the end of a line.

Commands can be read from a file specified via either of the following:

- .eil file_name in the input file
- -eil file_name at invocation of the executable

The eldo> prompt appears before the first simulation, unless:

- option DOSIMCIR is specified
- -DOSIMCIR used at invocation of the executable

To control simulation, use the following commands:
QUIT
LOAD
RUN
GO

```
CONT
NEXT
```

To check netlist elements, use the following commands:

```
DISPLAY
LIST
```

To handle simulation information, use the following commands:

```
STATUS
PRINT
DELETE
RESET
OPTRESET
```

To handle breakpoints, use the following commands:

```
STOP IF (expression)
STATUS BREAK n
DELETE <index>|ALL
```

To alter simulation conditions, use the following Eldo/SPICE commands:

```
.TRAN
.DC
. AC
.OP
.STEP
.TEMP
.ALTER
.NOISETRAN
```

To change stimuli, re-instantiate the device with new values:

```
Vxx n1 n2 <new_stimuli>
```

To change element/model parameters, or parameters, use:
SET
Use the command, eilout file_name, to redirect the outputs generated by specific Eldo interactive commands to the specified file. Errors are still displayed on the terminal window. Use the command, eilout stdout, to switch back to the default mode, where information is sent to the terminal window.

## To Read Information

```
STATUS [BREAK] shows breakpoints
status anal shows status of the current simulation
STATUS AC
shows the AC simulation command and stimuli
```

```
STATUS TRAN
STATUS DC
STATUS MC
STATUS PZ
STATUS EXTRACT
STATUS PLOT
STATUS PROBE
STATUS PRINT
STATUS PARAM
STATUS INPUT
STATUS SAVE
STATUS RESTART
STATUS MCMOD
STATUS MCPARAM
STATUS STAT
STATUS OPTION
\begin{tabular}{|c|c|}
\hline STATUS TRAN & shows the tran simulation command \\
\hline Status dc & shows the DC simulation command \\
\hline Status mc & shows the MC simulation command \\
\hline Status pz & shows the PZ simulation command \\
\hline Status extract & shows the expressions to extract \\
\hline Status plot & shows the . PLOт commands typed \\
\hline Status probe & shows the . Probe commands typed \\
\hline Status print & shows the .PRINT commands typed \\
\hline Status param & shows the parameters (.PARAM) \\
\hline Status input & shows the input stimuli \\
\hline Status save & shows the . SAVE commands issued \\
\hline Status restart & shows the .restart commands issued \\
\hline STATUS MCMOD & shows the MC specifications on models \\
\hline Status mcparam & shows the MC specifications on parameters \\
\hline status stat & shows the statistics at runtime \\
\hline Status option & shows all the options set inside Eldo \\
\hline
\end{tabular}
```


## PRINT <expression>

The PRINT command can be issued to display:

- Voltage or current (like plot command)
- Values from the extract-command language
- extract index where index is the key returned by status extract
- Values of Device/Models/Parameters; syntax is:

```
PRINT E (<device_name>[,W/L/AD/AS/PD/PS/NRD/NRS/AREA])
PRINT M (<model_name>,<parameter_name>)
PRINT P (<param_name>)
```

- OPTION <name>

Examples:

```
PRINT V(S)
PRINT V(S) + V(SS)
```

PRINT TPD (E,S)
Please note that the extract information issued through a PRINT command work only if the corresponding .EXTRACT command had been specified before running the simulation, or if Eldo is able to extract the information from the binary output file (.РLOT available, and general-purpose extraction language used).

## DISPLAY E string[*]

| LIST string* | List all elements whose name begins with string |
| :--- | :--- |
| LSMOD string* | List all models whose name begins with string |
| LSMODEV string* | List all elements which have string* as model |
| LSSUB string* | List all subcircuits whose name begins with string |
| LSSUBDEV string* | List all instances of the subcircuit whose name begins with <br> string |

## .LPTOP

This command requests Eldo to dump . PARAM names which are top parameters and which are not coming from a . Lib library file. This is useful when debugging circuits.

## .LDEVNODE

Returns the list of devices connected to a node.

## .LDEVNODE <node>

## .LNODEDEV

Returns the name of the pins a device is connected to. A device name must be specfified as an argument. For example:

M1 A B C D NMOS w=10u $1=3 u$
eldo> .Inodedev M1
will return:

M1. 1 A
M1. 2 B
M1. 3 C
M1. 4 D

## .LSXINST

Returns the list of X instances matching a condition (with wildcards).

```
eldo> .lsxinst <filter>
```


## TRACEI

```
tracei <node_name> [thresehold_value]
```

Returns the current contributions on the specified node. For example, under the eldo> prompt, you can specify:

```
eldo> tracei s 1.0e-8
```

IX(M4.1) $=-2.1725 \mathrm{E}-05$
IX(M9.1) $=2.1725 \mathrm{E}-05$
The two contributions are not dumped because they fall below the threshold 1.0e-08. This tracei command returns current contributions on the specified node ( s in this example): 1.0e8 is a threshold, optional.

## To Reset Several Features

RESET [PRINT|PLOT|PROBE|IC|NODESET|GUESS|EXTRACT]
Used to remove a set of commands.
RESET FILES
Rewind output files .cou and .chi.

## Options

## DC Control Options

## GMIN

NMAXSIZE
ITL1
GRAMP
NETSIZE
VMIN
VMAX

## Accuracy Control Options

```
ITOL
EPS
VNTOL
RELTOL
RELERR
PIVREL
```

```
PIVTOL
ABSTOL
FLXTOL
MAXORD
```


## Time-step Control Options

```
ZOOMTIME
STEP
STARTSMP
FREQSMP
OUT_RESOL
TRTOL
HMIN
ITL3
ITL4
FT
DCLOG
LVLTIM
LVLCNV
DVDT
RELVAR
ABSVAR
SAMPLE
HMAX
SPICDC
NOSPICDC
```

Options which can be set, but not reset:

```
SPIOUT
```

NEWTON
OSR
TRAP
GEAR
BE
PROBEOP
NOLAT
NWLAT
ANALOG
BBDEBUG
NOSIZECHK
QTRUNC
UNBOUND
LCAPOP

## Change Features

Some Eldo commands are available from interactive mode; they are:

```
.TRAN .AC .DC .OP .STEP .TEMP
.PLOT .PRINT .PROBE .EXTRACT .OPTION
.MEAS .FOUR .OPTFOUR
.NODESET .IC .GUESS
```

. SAVE . RESTART . USE . LIB
It is possible to change the stimuli in interactive mode. The complete line must be re-entered with new stimuli.

Example:

```
V1 1 2 PWL (0 0 20n 0 30n 5)
```

The program checks the component name, and applies the new stimuli.

## BUS

BUS <name> <type> <list_of_signals>
Define a bus. The bus command defines a bus with several different nodes by grouping them together.

```
<name> Name of the new bus
<type> Ignored (kept for Lsim compatibility)
<list_of_signals>
```

List of nodes composing the bus (msb...lsb).

## Example:

```
bus foo x A[0] A[1] A[2] A[3] clk reset
bus foo x A[0:3] clk reset
bus ADD x A0 A1 A2 A3 A4 A5
```


## [.]CHMOD

```
CHMOD <model1> <model2>
```

Replace the model <model1> by the model <model2> for all the devices using <model1> (can be used for M, Q, D, J models).

## DELETE

DELETE BREAK index
DELETE BREAK ALL
DELETE <cmd> index
delete is used to remove breakpoints used to stop Eldo at run time. The third syntax is used to remove the command corresponding to the index returned by the command STATUS <cmd>.

## DISABLE

```
DISABLE BREAK index
DISABLE BREAK ALL
```

disable is used to remove breakpoints used to stop Eldo at run time. Breakpoints can be enabled back using command enable.

## ENABLE

```
ENABLE BREAK index
ENABLE BREAK ALL
```

enable is used to re-activate breakpoints used to stop Eldo at run time, whenever these breakpoints have been disabled by DISABLE.

## FORCE

FORCE <node_name>=<value>
Force the node node_name to value after RISE_TIME or FALL_time depending on current value (see further information below). Used to impose a voltage on a node. If multiple FORCE are applied on the same node, the last command is used. If an input signal was applied on the node it will be ignored. The voltage imposed by force can be removed using release.

## HIGH

```
    HIGH <node_name>
```

Force the node node_name to highvoltage after rise_time (see further information below).

## LOW

LOW <node_name>
Force the node node_name to lowvoltage after fall_time (see further information below).

The previous three commands contain the parameters, highvoltage, lowvoltage, rise_time and fall_time. These parameters can be set using the . option command. For more information, see "Miscellaneous Simulation Control Options" on page 974.

## PWL

```
PWL <node_name> t1 v1 [t2 v2] ...
```

Force a PWL on the specified node <node_name> during transient simulation. tn are times relative to the current time. vn are the source values at t .

## RELEASE

RELEASE <node_name> ...
Release force on node. If a signal is present on node <node_name>, and if no force command had been applied on the node, then the signal is disabled (node will be computed by Eldo as any other node).

## SET

```
SET E (<element_name> [,W/L/AD/AS/PD/PS/NRD/NRS/]) [=] <value>
SET M (<model_name>,<parameter_name>) [=] <value>
SET P (<parameter_name>) [=] <value>
```

The Set command is used to change device geometries or models parameters. The parameter_name can be specified as a string parameter.

## SETBUS

SETBUS <hierarchical_name>[[<msb>:<lsb>]] <type> <value>
Set a value on a bus. The setbus command sets a value on the specified bus. Values may be specified as binary, octal, hexadecimal, or decimal. The bus bit accepts the standard digital values $1,0, \mathrm{X}$ and Z .

The command automatically sets all signals in a bus if the subscripted values are omitted. The default bit order is the European style $\mathrm{D}_{0} \ldots \mathrm{D}_{\mathrm{N}-1}$. Therefore, for a hierarchical base name that defines an 8-bit bus, the command:

```
setbus Xcircuit.port[0:7] b00001111
```

is equivalent to:

```
setbus Xcircuit.port b00001111
```

To use the American style $\mathrm{D}_{\mathrm{N}-1} \ldots \mathrm{D}_{0}$ bit order, you must specify the range of bits explicitly:

```
setbus Xcircuit.port[7:0] b00001111
```

The setbus command ignores the most significant portion of values that are wider than the specified bus. Therefore, if you set a value of hexadecimal 8 F to a 12 bit bus, the bus receives the value 0 F .

## Note

$\qquad$
This setbus syntax is different to the Eldo . setbus syntax used in the netlist .cir file. See ".SETBUS" on page 870 and ".SIGBUS" on page 880 . However, if you want to use the netlist syntax in interactive mode, specify the Eldo interactive command:
eldo>LSIM OFF

## TRANSITION

TRANSITION <node_name> TT VALUE [DELAY]
tr $\quad$ Transition Time
value $\quad$ Value of the signal after the transition
delay $\quad$ Time delay before the transition starts
Overwrite the signal which was on node <node_name> by a PWL:

```
Vxx <node_name> 0 PWL (<current_time> <current_value>
<current_time + DELAY> <current_value> <TT + DELAY> <VALUE>)
```


## To Control Execution

## LOAD <filename>

This command stops the current simulation, and causes Eldo to load the file <filename>. Extension .cir is assumed.

## SAVESIM <filename>

Eldo creates three files:

1. filename.eil

This file contains all the commands typed since the loading of the circuit file; it is possible to re-execute this set of functions by:

```
<eldo> -i circuit -eil filename.eil
```

2. filename.chi

This file contains the ASCII output
3. filename.cou

This file is the binary output file readable by graphic-postprocessors
Note
$\bar{\square}$ A $\cdot \mathrm{pz}$ file might be created if a $\cdot \mathrm{pz}$ card exists.

The files circuit.cou and circuit.chi are then reset.

## STOP IF <condition>

Set breakpoints in interactive mode. <condition> can refer to the sweep value, and/or any valid plot command.

The argument, soadetected, can be specified to specify a breakpoint on a safe operating area (SOA).

## Examples

```
STOP IF (SWEEP > 1n)
STOP IF ((SWEEP > 10n) && (V(S) > 2.5))
stop if(soadetected(mysoa))
```

Eldo will stop the first time the . soa labeled mysoa is violated. Wildcards are allowed in soadetected.

## STOP SIMU

Stop the current simulation; Eldo is then ready to run a new simulation.

## RUN

Restart the simulation.

```
RUN FOR <value> Run until the sweep value has changed of <value>
RUN UNTIL <value> Run until the sweep value reaches <value>
Run until the sweep value reaches <value>
```

Note
<value> can be a parameter, this must be specified on the .PARAM command in the netlist.

## NEXT [SIMU]

next

NEXT SIMU

Eldo will stop at the next sweep value.
Eldo will stop after the next simulation if .TEMP or . Step command are found.

## CONT

CONT

QUIT
QUIT
QUIT SIMU

Forces Eldo to continue the simulation(s) until breakpoints are encountered, or the requested number of simulation is completed.

Quit the application.
Stop current analysis.

## CONNECT XELGA

Used to connect Eldo to Xelga in Eldo standalone mode.

## VIEW plot_name

UNVIEW plot_name
Used for adding or removing signals whenever Xelga is connected to Eldo, running in interactive mode.

## Appendix E <br> Eldo Utilities

## Utility to Convert .chi to .cir

A standalone utility chi2cir converts an Eldo ASCII output (.chi) file into a netlist (.cir) file. The resulting netlist file is independent of any libraries (no .LIB/. INCLUDE required), and all information required for another simulation is inside the netlist file (providing that there were no commands such as . .NOTRC preventing the writing of the circuit description in the .chi file).

This could be useful to exchange testcases between user's avoiding library dependence and would also simplify the creation of different tests on the same circuit.

Once the circuit has been run once (to generate the .chi file), run this chi2cir utility to generate a testcase from this .chi output in order to modify some parameters/options to re-run other simulations.

## Usage

```
    chi2cir [chifile cirfile]
```

- chifile

Input filename, the Eldo ASCII output (.chi) file.

- cirfile

Output filename for the resulting netlist (.cir) file.
If no options are specified, the utility will prompt you for filenames.

## Example <br> chi2cir trigger.chi my_trigger1.cir

Once the original trigger.cir circuit had been run once (to generate the .chi file), running the chi2cir utility on the trigger.chi ASCII output file generates a testcase file my_triggerl.cir. Some parameters/options can then be modified in this testcase to re-run other simulations.

## Notes

- The chi2cir utility does not handle references to Verilog-A model files or S-parameters files.
- No provision is made for .alter statements for multiple simulation runs, only the first simulation is taken into account.


## Utility to Convert VCD to Test Vectors

A standalone utility vcd2tv can be used to convert VCD (Value Change Dump) stimuli into test vectors. It is a simple format converter, and can be used independently for any simulator. Output is in the test vector format. This utility can also be used to convert EVCD (extended VCD) files. Note when converting from EVCD format: inout statements are converted to input statements.

The ADiT fast SPICE simulator supports VCD directly because it internally converts it to test vector format, transparently using the ved2tv converter. Eldo is not able to read VCD, which is why this utility is useful. It can be used for any simulator which can read test vectors but not VCD.

After converting a VCD file, use the generated test vector file by specifying the .TVINCLUDE command.

## Usage

```
vcd2tv -i vcd_input_file [-io io_input_file] [-o tv_output_file]
```

[-hier] [-end_time conversion_end_time]

- -i vcd_input_file

Input filename. Name of the VCD file to convert.

- -io output_file

Input/output filename. Name of the file containing the I/O definition (input or output).

- -o tv_output_file

Output filename. Name of the test vector file (.tv) to generate.

- -hier

When specified hierarchical node names are also converted. If not specified, only the top level is converted.

- -end_time conversion_end_time

Conversion time limit (if not specified conversion is done until the end of the VCD file).

## Utility to Convert a Waveform Database

A standalone utility ffev can be used to convert a waveform database from one format to one, or several, other formats.

## Usage

```
ffcv input_database output_format_modifier [output_database]
    [-cvt_start xstart] [-cvt_stop xstop] [-cvt_tsample xvalue]
```

- input_database

Input filename with known extension. Name of the waveform database file to convert.

- output_format_modifier

Specification of the output format to generate. Can be one of the following:
Table E-1. ffcv Output Format Modifier

| output_format_modifier | Output Format |
| :--- | :--- |
| -cou | Binary COU file |
| -cou_ascii | Raw ASCII representation of a COU file |
| -comment | Commented ASCII representation of a COU file |
| -compat | Binary compatible file |
| -compat_ascii | ASCII compatible file |
| -csdf | CSDF file |
| -fsdb | FSDB file |
| -wdb | Joint Waveform Database file (Eldo default) |
| -stimuli | SPICE representation of voltage waveforms |
| -tabular | Tabulated representation of waveforms |
| -wdf | WDF file |

- output_database

Output filename. Name of the waveform database file to write converted format to.

- -cvt_start xstart

Conversion start point (time or frequency) in database.

- -cvt_stop xstop

Conversion end point (time or frequency) in database.

- -cvt_tsample xvalue

Time or frequency interval to sample output data.

Eldo Utilities
Utility to Convert a Waveform Database

## Appendix F Eldo Encryption

## Eldo Encryption

encrypt_eldo is the tool to encrypt the libraries containing . subскт definitions, .MODEL/. PARAM cards, and .PROTECT/. UNPROTECT blocks. It uses DES encryption with an internal 56-bit key. The file will be automatically decrypted by Eldo at run time, but none of the encrypted information will be displayed in the ASCII output file (.chi). This guarantees the confidentiality of the data.

See the .PROTECT and .UNPROTECT command descriptions for further information.
Caution
Apart from .PROTECT/.UNPROTECT blocks, .MODEL, .PARAM, and .SUBCKT commands will be encrypted.

## Usage

encrypt_eldo -i input_file [-o output_file] [-compat] [v]

- -i input_file

Input filename. The file can contain model cards, parameter cards, subcircuit definitions, and protected blocks for encryption.

- -o output_file

Output filename. If this is not specified, the filename will be input_file.crypt.

- -compat

Simulator compatibility argument. When specified only .PROTECT/. UNPROTECT blocks will be encrypted.

- -v

Returns the software version number. No encryption is performed.

## Example

1. Unencrypted netlist (diode.lib):
```
.model DNPPSJU
+ d level=8 diolev=9 tr=27 tnom=27
+ vr=0 cjbr=0.00072727 cjsr=8.649e-12
+ cjgr=3.946e-10 jsdbr=3.5987e-07 jsdsr=3.4372e-12
```

```
+ jsdgr=6.9543e-14 jsgbr=6.0153e-06 jsgsr=1.0506e-09
+ jsggr=6.4326e-10 vdbr=0.55572 vdsr=0.49482
+ vdgr=0.79381 pb=0.44466 ps=0.99
+ pg=0.43889 nbj=1 nsj=1.2
+ ngj=1
.subckt diode A B
.model my_diode D diolev=9 tr=27 tnom=27
+ vr=0 cjbr=0.00072727 cjsr=8.649e-12
+ cjgr=3.946e-10 jsdbr=3.5987e-07 jsdsr=3.4372e-12
R1 A A1 1k
D1 A1 B1 my_diode
R2 B1 B 1k
.ends
```

2. Command for encrypting this netlist with the Eldo license:
```
encrypt_eldo -i diode.lib -o diode_crypt.lib
```

3. Output file generated (diode_crypt.lib):
\%.model DNPPSJU
\%6A41CAC8CE3D50CB0B85F0126F6D1CCF23E5CA9C3BD0E7F21716251CB19DA7 \%36FBBF69EF23E826A0478CA39376DCC8C4B7DBCD4A5A61CD26999C7F74FA2C \%75D9133AD4A91885751DDCE235FB1D944B96A4491CE3EDC5247588A7697FA1 \%F912ED3488C832AB598321B58D3F25D176D794F6376924596B7948A4068996 \%35363770AA370F3C10331A8FC0B5822FFDA963774FFFC74F1FFA3021EA693F \%D88A1A3E8DDBC62012F317FE3BF379A999B6638BFE8A7A97E6B46C6E1E2B60 \%A2A9362162265083A1A898E5CF8EF5A5F6FF420A52C2E23FB9364E2BC13F29 \%6F79757FF86BB080DCBAA2B4FC7EBF863B3B0C7C896BAF6525DF00901CD9E1 \%6FC7E1BD4E691E6B006451AAE3302D64AD912114D5AC4F3D436BB1AAE5582F $\% 1 \mathrm{~A}$
```
.subckt diode A B
%A40ACD98849922AC0480 9D607E2424D4255F6765FF779A2EF4 9C24DC0
%483152A2024CA2B0C2E975EE8E41C1DCD2098C152082EA626C990AE64
%7B7F38B8FFEA9868E28164C55E19139F8378A9FF6BB9946CC7448D744
%127ADEA26B511101C631E3D455880E6E56EFBFEBC481964A7300C9FBF
%5B57245A6CC15D2A72BC833D8437DCF53D85F1B017366485676443756
%2BFFAC6DFEB58B5A43ACD64C30ECA1F7491380ED4F8777FBDF2BF6DA1
%287BD1F4C86D96B25ABA5164851F196324189F42BFC67116235368287
%5
.ends
```

4. Input file (test.cir)
```
* example for encryption netlist
.lib diode_crypt.lib
v1 1 0 1
d1 1 2 DNPPSJU
x1 2 0 diode
.op
.end
```


## 5. Invoking Eldo.

```
eldo test.cir
```


## Notes

The netlist is not displayed inside the Eldo output (.chi) file, as shown below:

```
.MODEL DNPPSJU ----> the lines 4 to 13 are not displayed here.
.SUBCKT DIODE A B -> the lines 16 to 23 are not here.
Warning 902: "DIOLEV in model DIODE.MY_DIODE": Model parameter ignored.
Warning 902: "TR in model DIODE.MY_DIODE": Model parameter ignored.
Warning 902: "VR in model DIODE.MY_DIODE": Model parameter ignored.
Warning 902: "CJBR in model DIODE.MY_DIODE": Model parameter ignored.
Warning 902: "CJSR in model DIODE.MY_DIODE": Model parameter ignored.
Warning 902: "CJGR in model DIODE.MY_DIODE": Model parameter ignored.
Warning 902: "JSDBR in model DIODE.MY_DIODE": Model parameter ignored.
Warning 902: "JSDSR in model DIODE.MY_DIODE": Model parameter ignored.
.ENDS
```

V1 101
D1 1 2DNPPSJU
X1 21 DIODE

The encrypted model parameters are not displayed inside the Eldo output .chi file.

## Protection of Encrypted Libraries

## Overview

An improved IP protection system is available, providing an additional level of protection compared to simple encryption available through the encrypt_eldo utility. This system is for IP providers with respect to their customers. The device model libraries provided by IP providers (typically foundries here) often contain process sensitive information such as SPICE device models, equations, technology parameters, and so on. These may be encrypted, but there is no easy way to restrict the usage of these encrypted model libraries. In particular, there is no way to restrict the allowed duration of usage. The purpose of the new IP protection system is to allow an IP provider to ship encrypted and licensed model libraries to their customers, independent of Mentor Graphics. The licensing mechanism might be a standard commercial license managing system. Using the system, the IP provider can control the usage of its model libraries in exactly the same way that any commercial software is controlled, using features, license files, expiration dates, and so on. The system is designed in such a way that Mentor Graphics does not have to know the final end-users, nor generate any keys nor licenses. The IP provider creates and provides both the encrypted IP (the model libraries) and an "IP access library". The IP access library is a dynamic load library (compiled C code). Mentor Graphics does not interfere with the encryption process, nor the license generation, maintenance, renewals, and so on, which are the entire responsibility of the IP provider.

The steps involved in preparing and installing a vendor-specific protected/encrypted library are as follows:

1. The vendor, or IP provider, prepares a single "IP access" library. This is a dynamic load library coded in C.
2. The vendor then prepares and encrypts the Eldo library source for each library the vendor wishes to distribute.
3. The user installs the vendor-specific IP access library and the vendor protected/encrypted libraries.
4. The user then installs the licensing software and keys provided by the IP vendor.

Figure F-1. IP Protection


## Coding and Encrypting a Protected Library

As an IP provider wishing to protect a library, you must include these specific commands in your library file (.lib):

```
.IP_protect IP_provider=<NameOfTheIPProvider>
+ IP_access_lib=<NameOfTheAccessLibrary> feature=<NameOfTheFeature>
+ ixl=<ixl_crc> ss5=<ss5_crc>
+ ixl64=<ixl64_crc> ssw=<ssw_crc>
```

The .IP_protect command must be written inside a .PROTECT/.UNPROTECT area of the device model library (.LIb). The device model library then has to be encrypted using the standard eldo encryption tool, encrypt_eldo, which is provided with the AMS distribution. As the IP_protect command is inside a .PROTECT/. unProtect area, it is encrypted as well, and therefore cannot be read nor changed by the final user. See the command description for ".PROTECT" on page 850 for further information.

The meaning of the items in the .Ip_protect command are explained below.

- IP_provider

The name of the IP provider, as it will appear in messages. Use a simple string comprising only letters (A-Z) and numbers (0-9). Do not use blanks.

- IP_access_lib

The name of the dynamic load library which communicates between Eldo and the actual license manager. Note that NameOfTheAccessLibrary must be given without its extension. Eldo will add the proper extension (such as ".so") according to the platform. This library will have to be located in a path listed in the LD_LIBRARY_PATH environment variable.

- feature

The feature name which will be checked-out to grant access to the protected library.

- ixl, ss5, ixl_64, ssw

These are CRC values of the IP access libraries, as returned by the eldo_checksum.exe utility provided in the AMS distribution. These CRC values must be provided, and are checked by Eldo to verify the integrity of the IP access library. The eldo_checksum.exe utility must be run once per physical platform.

## Description of the Loading and Control Process

Whenever an Eldo netlist contains a reference to an encrypted model library containing a . IP_protect command, Eldo reads the name of the IP access library from the . IP_protect command, and then dynamically loads that IP access library (NameOfTheAccessLib). This dynamic library is used as an interface between Eldo and the license daemon of the IP provider (or any other licensing manager). Eldo communicates with this dynamic library only to ask whether the loading of the model library is allowed, by calling a simple function. The dynamic library in turn communicates with the license manager of the IP provider. It is the IP provider's responsibility to provide the end-user with the daemon, license file, and so on.

If the access is granted, Eldo decrypts and loads the necessary devices from the .lib file, and runs the simulation. If access is denied, the simulation aborts. Notice that when using an encrypted library, the . LIB command in the netlist is a regular . LIB command (that is, whether the device model library is encrypted or not does not change the usage).

Eldo decides if access is granted or denied by calling a function in the IP access library. This function must be coded by the IP provider, and it is in charge of interrogating the provider's license daemon to grant/deny access to the necessary feature. This function is described later.

As it would be too easy to fool this system by replacing the IP access library by another dynamic library which always returns 'ALLOWED', Eldo verifies that the checksum of the loaded library is the same as the one specified in the .IP_protect command. That means that if a new IP access library is compiled, the . IP_protect command must be rebuilt, and the model library re-encrypted, as the CRC will have changed. Note that a CRC is platform dependent, and therefore several CRCs must be provided in the .IP_protect command to accommodate the various targeted platforms (ixl, ss5, and so on).

The standalone executable, eldo_checksum.exe, generates the CRC of the library. This is available in the standard AMS distribution, located in the \$MGC_AMS_HOME/\$VCO/bin directory.

For example, run:

## \$MGC_AMS_HOME/\$VCO/bin/eldo_checksum.exe <NameOfTheAccessLibrary>

where NameOfTheAccessLibrary is a .so file on Solaris or Linux. Specify this name without its extension.

The utility returns a CRC value which must be provided to the .IP_protect command. It must be run once for each platform.

The NameOfTheIPprovider character string is used to display proper messages to the final user if there is a problem during the license check-out.

## Creating the IP Access Library

The required Eldo interface of the IP access library must contain two functions, namely:

```
ty_lib_status * get_license_third_party(char *feature);
```

and

```
ty_lib_status * release_license_third_party(char *feature);
```

The ty_lib_status type and the function prototypes are defined in the eldo_ipprotect. $h$ include file, shown below. This is provided in the $\$ M G C_{-} A M S \_H O M E / i n c l u d e ~ f o l d e r . ~ T h e ~ v a r i o u s ~$ return values and their meanings are explained in the comments.

## Contents of eldo_ipprotect.h Include File

```
typedef enum
{
    /*! The license manager has successfully checked out the feature,
    * nothing special to do */
    getFeatureOk,
    /*! The license manager failed to check out the feature.
    * An error message will be printed and the simulation will stops.*/
    getFeatureNOk,
    /*! The license manager has checked out the feature, but a warning
    * should be printed
    * (for example: if the license is about to expire soon) */
    getFeatureOkWarn,
    /*! The license manager has released the feature, nothing special to do */
    releaseFeatureOk,
    /*! The license manager failed to release the feature. A warning message
    * will be printed and the simulation will continue.*/
    releaseFeatureNOk,
    /*! The license manager has released the feature, but a warning
```

```
    * should be printed */
    releaseFeatureOkWarn
} en_ipstatus;
/**
    * This structure is used by eldo to check the result of the license
    * request.
    */
typedef struct
{
    /* The status of the request. According to it some actions will be done.*/
    en_ipstatus status;
    /* The message that eldo must print. Once the message is printed, eldo
        * will free the memory allocated for the message.
        */
    char *message;
} ty_lib_status;
/**
    * \brief This function is used to check that the feature given in
    * argument is available. Eldo doesn't manage the possible queue
    systems. It is up to the library loaded by eldo to do that job.
    \param feature is the feature name (as it appears in the license file)
    needed to continue to parse the design
    \returns the status of the license check-out.
        If the license check-out failed, eldo will print the attached
    message as an error, will free it just after,
    and will abort the simulation. It will work the same way
    if the status is getFeatureOkWarn but the printed message
    will be a warning and it will not abort the simulation.
    *
ty_lib_status * get_license_thrd_party(char *feature);
/**
    * \brief That function is used to release the feature given in argument.
    * Eldo doesn't manage the possible queue systems. It is up to the
    library loaded by eldo to do that job.
    \param feature is the feature name that has been previously checked out
    and that must be released.
    * \returns the status of the license checkin.
    * If the license checkin failed, eldo will print the attached
        message as a warning and will free the message just after.
        The simulation will not be aborted. It will work the same way
        if the status is releaseFeatureOkWarn.
    */
ty_lib_status * release_license_thrd_party(char *feature);
```

The compilation command for the shared library is as follows:

## gcc -I\$MGC_AMS_HOME/include (...other include folders...) <NameOfTheCFile.c> -0 <NameOfTheSharedLibrary> -shared

This library does not need to be recompiled with each new version of Eldo unless this is explicitly stated in the release notes of a new version.

## Installing a Protected Library

For Eldo to be able lo load a protected library, the IP access library (a .so file on Solaris or Linux) must be located in a directory named .../ixl or .../ss5, and so on, depending on its binary origin (Linux, Solaris, and so on). The parent of that directory must be specified in the standard LD_LIBRARY_PATH variable.

For example:
Having received the foo.so library (for Linux 32) from your provider IpProvider, you want to put that library under the common shared folder/shared/common/thirdPartyLibs. You must create a specific folder according to the platform of the foo.so library. In this example it is a Linux 32-bit library so put the file under/shared/common/thirdPartyLibs/ixl.

The path to include in the LD_LIBRARY_PATH variable is/shared/common/thirdPartyLibs. Eldo will automatically search under the ixl folder if it is run on the Linux 32-bit system.

## List of Errors and Warnings

The various "\%s" appearing in these messages are place-holders for the actual names of the libraries, names, and so on.

```
ERROR 1608: Wrong vendor library, found at:\n+ %s\n+ The CRC of that
library is not the expected one. Please contact your %s office.
```

The checksum made on the found library does not match the one specified in the netlist.

```
ERROR 1609: Unable to find the %s%s dynamic library provided by %s.\n+
Check first your LD_LIBRARY_PATH. It must contain the path to %s/%s%s.\n+
If you don't have that library, please contact your %s office to get one.
```

Eldo was not able to find the requested library through the folder given in the
LD_LIBRARY_PATH variable (with respect to the rule specified above).

```
ERROR 1610: The protected part of the %s design requires a license to be
used. Eldo is unable to get a valid license feature %s\n+ %s"
```

Checkout of the license has failed.

```
ERROR 1611: Shared library %s%s was found but an error occured during its
loading.\n+ Please contact %s office.
```

An unexpected error has occurred (there was a missing function, the simulation was aborted before, the crc has been changed, and so on).

```
ERROR 1612: Wrong vendor library %s%s found. The CRC of that library is
not the expected one. Please contact your %s office.
```

The checksum made on the found library does not match the one specified in the netlist.

```
ERROR 1616: In command .IP_Protect, missing %s parameter or parameter
value.
```

The command contains one or several parameters that have no value, or a mandatory parameter has been forgotten.

```
ERROR 1618: Command .IP_Protect is not supported on that platform.
```

You have tried to run a circuit protected by ip_protect on a Windows platform. (Windows is not supported.)

```
ERROR 1619: Errors occur during command .IP_Protect: aborting the
simulation.
```

This appears at the end of the command if an error occurred before.

```
ERROR 1620: Fatal error while %s license %s from provider %s.\n+ Please
contact your provider for more details.
```

Eldo is unable to get a proper return value when trying to check-out or check-in the license.

```
ERROR 1621: Fatal error while loading shared library %s%s.\n+ Please
contact %s office."
```

Eldo is unable to load the dynamic library.

```
Warning 1447: Unable to release %s license, feature %s\n+ %s
```

The license check-in failed.

```
Warning 1476: License message from Provider: %s - Feature: %s\n+
&quot;%s&quot;
```

The license tool has a specific message to deliver to the end user.

## Appendix G STMicroelectronics Models

## Introduction

This section describes how to use the ST models inside Eldo, which in this case is called Eldo-ST.

## How to Invoke Eldo-ST

Eldo-ST is invoked as follows:
eldo -stver ... cir_file_name
or by adding before the .MODEL cards the following:
.OPTION STVER
In case you want to disable the Eldo-ST mode, you can use the Eldo command-line argument:
eldo -nostver ... cir_file_name
or add before the .model cards the following:

## .OPTION NOSTVER

In all cases, the . option takes precedence.

## What Does it Change?

When Eldo-ST is invoked, model levels are automatically changed to use Eldo-ST in exactly the same way as ST-SPICE:

Table G-1. Eldo/Eldo-ST Model Levels

| Component | Eldo | Eldo-ST |
| :---: | :---: | :---: |
| MOS | . Model . . . Level= 18 or Level=STMOS1 | . Model . . . LEVEL=1 |
|  | . Model . . . Level=19 or Level=STMOS3 | . Model . . . Level=3 |
| Bipolar | . MODEL . . . LEVEL=2 | . MODEL . . . LEVEL=1 |
| Diode | . MODEL . . . LEVEL=4 | . MODEL . . . LEVEL=1 |
|  | . Model . . . Level=5 | . Model . . . Level= $=2$ |
|  | . Model . . . Level=6 | . Model . . . level=3 |

Table G-1. Eldo/Eldo-ST Model Levels

| Component | Eldo | Eldo-ST |
| :---: | :---: | :---: |
| JFET | .MODEL . . LeVEL=4 | . Model . . . Level= 1 |
|  | . Model . . . level=5 | . Model . . . Level=2 |
| Resistor | . Model . . . Level=2 | . Model . . . Level=1 |

All the standard Eldo levels may be used in Eldo-ST by adding the following in the .model card:

MODTYPE=ELDO

## STMicroelectronics Version of Eldo

Specially tuned device models have been developed for use when simulating STMicroelectronics designs. These STMicroelectronics models are available within the standard version of Eldo, for example as can be seen from the list of diode models available:

Table G-2. STMicroelectronics Model Selection

| Lever Value | Model Name |
| :--- | :--- |
| 1 | Berkeley Level 1 |
| 2 | Modified Berkeley Level 1 |
| 3 | Fowler-Nordheim |
| 4 | STMicroelectronics Level 1 |
| 5 | STMicroelectronics Level 2 |
| 6 | STMicroelectronics Level 3 |

A special version of Eldo is also available which has been developed for use within the STMicroelectronics design kit. This version is identical to the standard version in every respect except that the STMicroelectronics device models occupy different levels within the lists of available device models. The different device model levels used within the STMicroelectronics version of Eldo are listed below:

Junction Diode Models

Table G-3. STMicroelectronics Junction Diode Model Selection

| Levei Value | Model Name |
| :--- | :--- |
| 1 | STMicroelectronics Level 1 |
| 2 | STMicroelectronics Level 2 |

Table G-3. STMicroelectronics Junction Diode Model Selection

| Leved Value | Model Name |
| :--- | :--- |
| 3 | STMicroelectronics Level 3 |

## MOSFET Models

Table G-4. STMicroelectronics MOSFET Model Selection

| Levei Value | Model Name |
| :--- | :--- |
| 1 | STMicroelectronics Level 1 |
| 3 | STMicroelectronics Level 3 |

## Bipolar Junction Transistor Model

Table G-5. STMicroelectronics BJT Model Selection

| Level Value | Model Name |
| :--- | :--- |
| 1 | STMicroelectronics Level 1 |

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

## - Symbols -

! comment delimiter, 70
\# symbol
test vector file comments, 921

* comment delimiter, 70
.A2D, 102, 528
.AC, 102, 538
.NOISE, 744
.PLOT, 796, 835
.PRINT, 830 to 831
.PROBE, 839
Examples, 1342, 1345, 1349, 1353, 1363, 1465, 1474
.ADDLIB, 103, 544
.ALTER, 550
.MODEL, 723
.SUBCKT, 898
.AGE, 103, 546
.AGE_LIB, 103, 547
.AGEMODEL, 103, 548
.ALTER, 104, 549
-compat flag, 553
.BIND, 104, 554
.BINDSCOPE, 104, 558
.CALL_TCL, 104, 559
.CHECKBUS, 104, 561
.CHECKSOA, 104, 564
.SETSOA, 872
.CHRENT, 104, 567
.CHRSIM, 105, 569
.cir File Structure Overview, 69
.COMCHAR, 105, 571
.CONNECT, 105, 573
.ALTER, 549
.CONSO, 105, 574
.ALTER, 549
.CORREL, 105, 575
.D2A, 105, 577
.DATA, 105, 585
.DC, 105, 588
.PARAM, 778
.PLOT, 796, 835
.PRINT, 830
.PROBE, 839
.DCHIZ, 595
.DCMISMATCH, 596
.DEFAULT, 600
.DEFMAC, 106, 601
.EXTRACT, 643
.PARAM, 778
.DEFMOD, 106
.DEFPLOTDIG, 106, 604, 823
.DEFWAVE, 106, 605
.PARAM, 778
.PLOT, 797
.PRINT, 810 to 831
.DEL, 106, 610
.DEX, 106, 611
.DISCARD, 107, 612
.DISFLAT, 107, 613
.DISTRIB, 107, 614
.DSP, 107, 615
.DSPF_INCLUDE, 107, 617
.DSPMOD, 107, 625
.END, 107, 631
.ALTER, 549
INCLUDE, 685
.ENDL, 108, 632
.ENDS, 108, 633
.SUBCKT, 898
.EQUIV, 108, 634
.EXTMOD, 636
.EXTRACT, 108, 637
.ALTER, 549
.DEFMAC, 601
.DEFWAVE, 607
.MC, 707
.PARAM, 778
.FFILE, 108, 667
.FILTER, 669


## ABCDEFGHIJKLMNOPQRSTUVWXYZ

.FORCE, 108, 672
.FOUR, 108, 673
.FUNC, 675
.GLOBAL, 108, 676
.ALTER, 549
.SUBCKT, 898
.GUESS, 108, 677
.LOAD, 698
.NODESET, 743
.SAVE, 857
.USE, 926
.HDL, 678
.HIER, 109, 680
.IC, 109, 682
.LOAD, 698
.SAVE, 857
.USE, 926
.IGNORE_DSPF_ON_NODE, 684
.INCLUDE, 109, 685
.ALTER, 549
.INIT, 109, 688
.IPROBE, 109, 689
.LIB, 109, 692
.MODEL, 723
.SUBCKT, 898
Interactive mode, 695
.LOAD, 109, 698
.LOOP, 109, 699
.LOTGROUP, 109, 701
.LSTB, 109, 703
.MALIAS, 109
.MAP_DSPF_NODE_NAME, 705
.MC, 110, 706
.ALTER, 550
.SETSOA, 872
Examples, 1363
.MCMOD, 110, 715
.MEAS, 110, 717
.MODDUP, 110, 722
.MODEL, 110, 723
Examples, 1349, 1353, 1356, 1359, 1363, 1366
.MODEL ... LOGIC, 100, 449
.MODLOGIC, 727
.MONITOR, 728
.MPRUN, 729
.MSELECT, 111, 737
.NET, 111, 740
.NEWPAGE, 111, 741
.NOCOM, 111, 742
.NODESET, 111, 743
.GUESS, 677
.LOAD, 698
.SAVE, 857
.USE, 926
.NOISE, 111, 744
.PLOT, 796, 835
.PRINT, 830 to 831
.PROBE, 839
Examples, 1036, 1349
.NOISE_CORREL, 746
.NOISETRAN, 111, 747, 1025
Examples, 1031, 1040
.NOTRC, 111, 752
.NWBLOCK, 112, 753
.OBJECTIVE, 754
.OP, 112, 755, 761
.ALTER, 549
.OPTFOUR, 112, 764
.OPTIMIZE, 112, 770
.OPTION, 112
.ALTER, 549
.PROBE, 838
.TRAN, 912
Examples, 1342, 1356, 1359, 1363
see also Options
.OPTNOISE, 112, 772
.OPTPWL, 113, 776
.OPTWIND, 113, 777
.PARAM, 113, 778
.ALTER, 549
.MODEL, 724
.SUBCKT, 898
-compat flag, 786
Examples, 1359
Multiple Affectation of Parameters, 786
.PARAMDEX, 788
.PARAMOPT, 789
.PART, 113, 790
.PLOT, 113, 791

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

.AC, 539
.ALTER, 549
.CHRSIM, 569
.MC, 707
.NOISE, 744
-compat flag, 801
Examples, 1342, 1345, 1349, 1353, 1356, 1359, 1363
.PLOTBUS, 114, 827
.PRINT, 114, 830
.AC, 539
.ALTER, 549
.MC, 707
.NOISE, 744
.PROBE, 831, 842
.STEP, 893
.PRINTBUS, 114, 832
.PRINTFILE, 835
.PROBE, 114, 838
.PROBEBUS, 848
.PROTECT, 114, 850
.PZ, 114, 851
.RAMP, 114, 852
DC Operating Point Calculation, 1080
.RESTART, 114, 854
.SAVE, 857
.SAVE, 115, 857
.LOAD, 698
.USE, 926
DC Operating Point Calculation, 1082
End of Simulation Results, 1083
.SCALE, 860
.SELECT_DSPF_ON_NODE, 862
.SENS, 115, 863
.ALTER, 549
Examples, 1366
.SENSAC, 865
.SENSPARAM, 115, 867
.SETBUS, 115, 870
.PLOTBUS, 827, 832, 848
.SIGBUS, 880
.SETKEY, 115, 871
.SETSOA, 115, 872
.CHECKSOA, 564
.SIGBUS, 880
.PLOTBUS, 827, 832, 848
.SETBUS, 870
.SINUS, 116, 884
.SNF, 116, 885
.SOLVE, 116, 887
.START_TIME, 889
.STEP, 116, 890
.ALTER, 550
.PARAM, 778
.SAVE, 858
.SETSOA, 872
.SUBCKT, 117, 898
.PARAM, 779, 785
.PRINT, 809 to 818
Examples, 1353
Subcircuit Instance, 301
.SUBDUP, 117, 904
.TABLE, 117, 905
.TCL_WAVE, 906
.TEMP, 117, 907
.SETSOA, 872
Resistor Model, 129, 312, 319
.TF, 117, 908
.TITLE, 117, 909
.TOPCELL, 117, 910
.TRAN, 117, 911
.PLOT, 796, 835
.PRINT, 830
.PROBE, 839
-compat flag, 913
Examples, 1345, 1356, 1359, 1460, 1461, $1467,1469,1472,1477,1480$
UIC Parameter, 135, 141, 672, 682
.TSAVE, 118, 916
.TVINCLUDE, 118, 918
.UNPROTECT, 118, 925
.USE, 118, 926
.SAVE, 857
DC Operating Point Calculation, 1082
.USE_TCL, 118, 929, 1255
.USE_VERILOGA, 931
.USEKEY, 118, 928
.VEC, 118, 932
.VERILOG, 933
.WCASE, 934

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

.SETSOA, 872
.WIDTH, 118, 938
/* .. */ comments in test vector files, 921

## - Numerics -

2-Input Digital Gates, 100
2-port Parameters
see Two-port Parameters
3-Input Digital Gates, 100, 459
4-bit Adder Example, 1461
4th Order Butterworth Filter Tutorial, 1345
5th Order Elliptic SC Low Pass Filter Example, 1469

- A -

ABS (Absolute value), 78
ABSTOL option, 963
ABSVAR option, 963
AC Analysis (.AC)
.AC, 538
.LOOP, 700
.MC, 706
.NOISE, 744
.PRINT, 805, 808, 810
.PZ, 851
Examples, 1342, 1345, 1349, 1353, 1465, 1474
AC Noise Analysis
(.OPTNOISE), 772

AC Sensitivity Analysis (.SENSAC), 865
ACCSEMICOL option, 950
Accuracy
by Time Window (.OPTPWL), 776
by Time Window (.OPWIND), 777
EPS Parameter, 302, 484, 899, 1457
VNTOL parameter, 1457
ACDERFUNC option, 983
ACM option, 983
ACOS (Arc cosine of value), 78
ACOUT option, 997
Active RC Band Pass Filter Example, 1474
A-D Converter Macromodel, 101, 463
Adder Macromodel, 100, 444
Parameters, 444
Adder, Subtractor, Multiplier, Divider Macromodels

Parameters, 444
ADJSTEPTRAN option, 963
Admittance parameters, 1041
AEX option, 1010
Age Analysis (Reliability), 546
AIDSTP option, 963
ALIGNEXT option, 1011
ALT
.SAVE, 858
ALTER_ADDSTEP option, 951
ALTER_NOMINAL_TEXT option, 998
ALTER_SUFFIX option, 998
ALTERELDO option, 951
ALTINC option, 951
AMMETER option, 974
Amodel Error Messages, 1431
Amplitude Modulation Function, 323
Amplitude Modulator Macromodel, 98, 417
Characteristics, 418
Parameters, 417
Analog Macromodels, 97 to 100, 379
ANALOG option, 1016
Analysis
AC (.AC), 538
AC Sensitivity (.ACSENSRLC), 865
DC (.DC), 588
DC Sensitivity (.SENS), 863
Loop Stability (.LSTB), 703
Monte Carlo (.MC), 706
Noise (.NOISE), 744
Noise (.OPTNOISE), 772
Pole-Zero (.PZ), 851
Sensitivity (.SENSPARAM), 867
Transient (.TRAN), 911
Worst Case (.WCASE)
.MC, 707
AND Gate
see Double, Triple and Multiple Input Digital Gates
Anti-logarithmic Amplifier Macromodel, 99, 438
Parameters, 438
Applications
of Switched Capacitor Macromodels, 512
Euler Forward Integrator, 515

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

LDI Phase Control Euler Backward Integrator, 518
LDI Phase Control Euler Forward Integrator, 516
LDI Phase Control Non-inverting Integrator, 514
Non-inverting Integrator, 513
Arithmetic Functions \& Operators
ABS(VAL), 78
ACOS(VAL), 78
ASIN(VAL), 78
ATAN(VAL), 78
BITOF (a, b), 79
CEIL(VAL), 79
COMPLEX(), 79
CONJ(), 79
COS(VAL), 78
COSH(VAL), 78
DB(VAL), 78
DDT(VAL), 79
DERIV(VAL), 79
DMAX(VAL1, ..., VALn), 79
DMIN(VAL1, ..., VALn), 79
EXP(VAL), 78
IDT(VAL), 79
IMAG(), 79
INT(VAL), 78
LIMIT(a, b, c), 79
LOG(VAL), 78
LOG10(VAL), 78
MAGNITUDE(), 79
MAX(VAL1, ..., VALn), 79
MIN(VAL1, ..., VALn), 79
MOD, 80
ONGRID( ), 80
POW(VAL1, VAL2), 78
PWL( ), 79, 80, 605, 606
PWR(VAL1, VAL2), 78
REAL(), 79
ROUND(VAL), 79
SELECT( ), 80
SGN(VAL), 78
SIGMA, 80
SIGN(VAL), 78
SIGN(VAL1, VAL2), 78

SIN(VAL), 78
SINH(VAL), 78
SMABS, 80
SMMAX, 80
SMOOTHMIN, 80
SMSGN, 80
SMSIGN (Signum value), 80
SQRT(VAL), 78
STOSMITH(), 79
TAN(VAL), 78
TANH(VAL), 78
TRUNC(VAL), 79
YTOSMITH(), 79
ZTOSMITH(), 79
Arithmetic Functions \& Operators in Eldo
Arithmetic Functions, 78
Arithmetic operators, 83
Bitwise operators, 84
Boolean operators, 83
-compat flag, 82, 1383
Expressions, 84
ASCII option, 998, 1011
ASCIIPLOT option, 998
ASIN (Arc sine of value), 78
ASPEC option, 983
ATAN (Arc tangent of value), 78
A-to-D Converter
.A2D, 528
Automatic Ramping (.RAMP), 852
AUTOSTOP option, 974
AUTOSTOPMODULO option, 975
AVERAGE (extract function), 646
———
Band Pass Filter Tutorial, 1349
BE option, 1016
Berkeley BSIM3v2 (Level 47) MOSFET
Model, 272
Berkeley BSIM3v3 (Level 53) MOSFET
Model, 273
Berkeley BSIM4 (Level 60) MOSFET Model, 284
Berkeley BSIMSOI3 (Level 55) MOSFET Model, 277
Berkeley BSIMSOI3 (Level 56) MOSFET
Model, 279

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Berkeley BSIMSOI4.0 (Level 72) MOSFET Model, 292
Berkeley Level 1 Diode Model, 229
Parameters, 229
Berkeley SPICE BSIM1 MOSFET Model, 267
Berkeley SPICE BSIM2 MOSFET Model, 268
Berkeley SPICE MOSFET Models (Levels 13), 265

Bi-linear Switched Capacitor Macromodel, 102, 508
Equations, 509
Parameters, 508
Binning parameters, 257, 988
Bipolar Amplifier Tutorial, 1366, 1369
Bipolar Junction Transistor (BJT) Models .SENS, 863
BJT Model Syntax, 235
HICUM Model (Eldo Level 9), 239, 242
Mextram 503.2 Model, 237
Mextram 504, 240
Mextram 504 Model, 240
Modella Model, 241
Modified Gummel-Poon
Parameters, 237, 238
STMicroelectronics, 1511
Syntax, 92
VBIC v1.1.5, 239
Parameters, 239
VBIC v1.2, 238
Parameters, 239
BITOF, 79
Bitwise operators, 84
BLK_SIZE option, 998
BLOCKS=IEM option, 1016
BLOCKS=NEWTON option, 1016
Boolean operators, 83
BSIM3VER option, 984
BSLASHCONT option, 951, 960
BTA HVMOS Model, 295
Bus Creation, 870
Bus Signals
Checking, 104, 561
Plotting of, 827, 832, 848
Setting of, 116, 880
voltage threshold, $827,832,848$

## - C -

CADENCE Compatibility
see Options
Calculation of Transfer Function (.TF), 908
Call Tcl Function, 104
.CALL_TCL, 559
Capacitor Model, 90, 133, 137
.LOOP, 699
Parameters, 137
CAPANW option, 963
CAPTAB option, 998
CARLO_GAUSS option, 975
Cascaded Inverter Circuit, 35
CEIL (Value rounded up to integer), 79
Change comment character (.COMCHAR), 571
Charge Control in MOS Models 4 and 6 Example, 1472
Check Bus Signal (.CHECKBUS), 561
Check Safe Operating Area Limits (.CHECKSOA), 564

CHECKDUPL option, 951
CHGTOL option, 963
Chi file output, 86
Convergence Information, 87
Grounded Capacitors Information, 86
Matrix Information, 87
Newton Block Information, 87
Node \& Element Information, 86
chi2cir utility, 1495
Circuit Partitioning (.PART), 790
Circuit Temperature
Setting of (.TEMP), 907
CKDCPATH option, 951, 1380
Classification of Error Messages, 1411
CMOS Operational Amplifier (Closed Loop) Example, 1467
CMOS Operational Amplifier (Open Loop) Example, 1465
CODEFILE keyword in test vector files, 920
COLLAPSE_DSPF_OUTPUT option, 999
Colpitts Oscillator Tutorial, 1356
COMJ (Conjugate of complex number), 79
Command
Error Messages, 1423

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Warning Messages, 1443
Command Description
.A2D, 102, 528
.AC, 102, 538
.ADDLIB, 103, 544
.AGE, 103
.AGE_LIB, 103
.AGEMODEL, 103, 548
.ALTER, 104, 549
.BIND, 104, 554
.BINDSCOPE, 104, 558
.CALL_TCL, 104, 559
.CHECKBUS, 104, 561
.CHECKSOA, 104, 564
.CHRENT, 104, 567
.CHRSIM, 105, 569
.COMCHAR, 105, 571
.CONNECT, 105, 573
.CONSO, 105, 574
.CORREL, 105, 575
.D2A, 105, 577
.DATA, 105, 585
.DC, 105, 588
.DCHIZ, 595
.DCMISMATCH, 596
.DEFAULT, 106, 600
.DEFMAC, 106, 601
.DEFMOD, 106, 603
.DEFPLOTDIG, 106, 604
.DEFWAVE, 106, 605
.DEL, 106, 610
.DEX, 106, 611
.DISCARD, 107, 612
.DISFLAT, 107, 613
.DISTRIB, 107, 614
.DSP, 107, 615
.DSPF_INCLUDE, 107, 617
.DSPMOD, 107, 625
.END, 107, 631
.ENDL, 108, 632
.ENDS, 108, 633
.EQUIV, 108, 634
.EXTMOD, 108, 636
.EXTRACT, 108, 637
.FFILE, 108, 667
.FILTER, 669
.FORCE, 108, 672
.FOUR, 108, 673
.FUNC, 675
.GLOBAL, 108, 676
.GUESS, 108, 677
.HDL, 678
.HIER, 109, 680
.IC, 109, 682
.IGNORE_DSPF_ON_NODE, 109, 684
.INCLUDE, 109, 685
.INIT, 109, 688
.IPROBE, 109, 689
.LIB, 109, 692
.LOAD, 109, 698
.LOOP, 109, 699
.LOTGROUP, 109, 701
.LSTB, 109, 703
.MALIAS, 109, 704
.MAP_DSPF_NODE_NAME, 705
.MAP_DSPFNODE_NAME, 109
.MC, 110, 706
.MCMOD, 110, 715
.MEAS, 110, 717
.MODDUP, 110, 722
.MODEL, 110, 723
.MODLOGIC, 727
.MONITOR, 728
.MPRUN, 110, 729
.MSELECT, 111, 737
.NET, 111, 740
.NEWPAGE, 111, 741
.NOCOM, 111, 742
.NODESET, 111, 743
.NOISE, 111, 744
.NOISE_CORREL, 746
.NOISETRAN, 111, 747, 1025
.NOTRC, 111, 752
.NWBLOCK, 112, 753
.OBJECTIVE, 754
.OP, 112, 755, 761
.OPTFOUR, 112, 764
.OPTIMIZE, 112, 770
.OPTION, 112, 771, 939 to 1022
.OPTNOISE, 112, 772

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

.OPTPWL, 113, 776
.OPTWIND, 113, 777
.PARAM, 113, 778
.PARAMDEX, 788
.PARAMOPT, 789
.PART, 113, 790
.PLOT, 113, 791
.PLOTBUS, 114, 827
.PRINT, 114, 830
.PRINTBUS, 114, 832
.PRINTFILE, 114, 835
.PROBE, 114, 838
.PROBEBUS, 848
.PROTECT, 114, 850
.PZ, 114, 851
.RAMP, 114, 852
.RESTART, 114, 854
.SAVE, 115, 857
.SCALE, 860
.SELECT_DSPF_ON_NODE, 862
.SENS, 115, 863
.SENSAC, 865
.SENSPARAM, 115, 867
.SETBUS, 115, 870
.SETKEY, 115, 871
.SETSOA, 115, 872
.SIGBUS, 116, 880
.SINUS, 116, 884
.SNF, 116, 885
.SOLVE, 116, 887, 888
.START_TIME, 889
.STEP, 116, 890
.SUBCKT, 117, 898
.SUBDUP, 117, 904
.TABLE, 117, 905
.TCL_WAVE, 906
.TEMP, 88, 117, 907
.TF, 117, 908
.TITLE, 117, 909
.TOPCELL, 117, 910
.TRAN, 911
.TSAVE, 118, 916
.TVINCLUDE, 118, 918
.UNPROTECT, 118, 925
.USE, 118, 926
.USE_TCL, 118, 929
.USE_VERILOGA, 931
.USEKEY, 118, 928
.VEC, 932
.VERILOG, 933
.WCASE, 118, 934
.WIDTH, 118, 938
Command Line operation
-cou47, 45
Commands, 519
Comment Lines in Eldo, 70
comments
test vector files, 921
Common Netlist Errors, 1457
Comparator Macromodel, 97, 381
-compat flag
.ALTER, 553
.PARAM, 786
.PLOT, 801
.TRAN, 913
Arithmetic Functions \& Operators in Eldo, 82, 1383
COMPAT option, 950
Compatibility
HSPICE, 1373 to 1383
Spectre, 1395 to 1410
TIspice, 1384 to 1394
COMPEXUP option, 951, 1381
COMPLEX (Complex number function), 79
COMPMOD option, 950
COMPNET option, 950
Component Names in Eldo, 71
COMPRESS (extract function), 646
Conditions of DC Analysis (.NODESET), 743
Configuration of Simulator (.OPTION), 771, 939
Configure Spice Descriptions
.BIND, 554
Connect Two Nodes (.CONNECT), 573
Constant Gain Circles
see Two-port Constant Gain Circles
Continuation Lines in Eldo, 70
CONTINUE_INCLUDE option, 952
CONTINUOUS_FFT option, 999
Control Language, 69

## A B C DEFGHIJKLMNOPQRSTUVWXYZ

Control options (.OPTION), 771, 939
Control page layout (.NEWPAGE), 741
Convergence Information in Eldo, 87
Correlation Coefficient, 575
COS (Cosine of value), 78
COSH (Hyperbolic cosine of value), 78
COU, 47
COU option, 1011
-cou47
Running from the Command Line, 45
Coupled Inductor Model, 90, 147
CPTIME option, 975
Create Bus (.SETBUS), 870
CROSSING (extract function), 647
CSDF, 47
CSDF option, 1011
CSHUNT option, 1017
CTEPREC option, 1021
Current Controlled Current Source, 358
Current Controlled Switch Macromodel, 98, 404
Current Controlled Voltage Source, 371
Current Limiter Macromodel, 399
Current Probe (.IPROBE), 689
Current Used by a Circuit (.CONSO), 574

- D -

D_WA (extract function), 647
D2A
Logical states, 582
D2DMVL9BIT option, 1018
D-A Converter
.D2A, 577
D-A Converter Macromodel, 101, 465
Databases
Loading, 45
DB (Value in decibels), 78
DC Analysis (.DC), 588
.IC, 682
.MC, 706
.NODESET, 743
.OP, 755
.PRINT, 802
.SOLVE, 887
RELTOL, 887
.STEP, 893

Switch Macromodel, 488
DC Analysis Conditions (.NODESET), 743
DC Analysis High Impedance Detection (.DCHIZ), 595

DC Mismatch Analysis (.DCMISMATCH), 596
DC Operating Point, 538, 588, 677, 743, 852, 967, 973, 1079
.RAMP, 852
DC Operating Point Calculation (.OP), 755, 761
.SAVE and .USE, 1082
DC Sensitivity Analysis (.SENS), 863
DC Sweep, 590
.CHRSIM, 569
DCLOG option, 1021
DCM (extract function), 647
DCPART option, 1017
DDT (Derivative of value), 79
DEFA2D option, 1018
DEFAD option, 984
DEFAS option, 984
DEFAULTFALLTIME option, 975
DEFAULTRISETIME option, 975
DEFCONVMSG option, 1018
DEFD2A option, 1018
Define Functions For Reliability, 547
Define local scope for .BIND
.BINDSCOPE, 558
DEFL option, 252, 984
DEFNRD option, 984
DEFNRS option, 984
DEFPD option, 984
DEFPS option, 984
DEFPTNOM option, 976
DEFRMSNTR option, 999
DEFW option, 252, 984
Delay Macromodel, 98, 100, 394, 453
DERIV (Derivative of value), 79
Design of Experiments, 1227
Design of Experiments (.DEX), 611
Device Description
Berkeley BSIM3v2 (Level 47) Model, 272
Berkeley BSIM3v3 (Level 53) Model, 273
Berkeley BSIM4 (Level 60) Model, 284

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Berkeley BSIMSOI3 (Level 55) Model, 277
Berkeley BSIMSOI3 (Level 56) Model, 279
Berkeley BSIMSOI4.0 (Level 72) Model, 292
Berkeley SPICE BSIM2 MOSFET Model, 268
Bipolar Junction Transistor (BJT), 232
Capacitor, 133
Coupled Inductor, 90, 147
Diffusion Resistor, 154
Diode, 225
Enhanced Berkeley SPICE Level 2 (Level 17) Model, 270

Inductor, 140
Junction Diode, 92, 225
Junction Field Effect Transistor (JFET), 244
Lossy Transmission Line, 91, 165
U Model, 192
U model, 91
W Model, 181
W model, 91
Metal Field Effect Transistor (MESFET), 92, 248
Metal Oxide Field Effect Transistor (MOSFET), 92
MOSFET Models, 249
Berkeley SPICE BSIM2, 268
BTA HVMOS (Level =101), 295
EKV MOS (Level =EKV or 44), 271
EKV3 MOS (Level =EKV3 or 61), 286
Modified Berkeley SPICE Level 2
(Level 12), 269
Modified Berkeley SPICE Level 3
(Level 13), 270
Modified Lattin-Jenkins Grove Model
(Level 16), 270
Motorola SSIM (Level 54 or SSIM) Model, 276
Philips MOS 9 (Level 59 or MOSP9) Model, 283
Philips PSP (Level 70) Model, 291
PSP103 (Level 75) Model, 295

RC Wire, 148
Resistor, 122
S-Domain Filter, 92, 297
Semiconductor Resistor, 90, 156
Subcircuit Instance, 93, 301
TFT Amorphous-Si (Level 64) Model, 287
TFT Polysilicon (Level 62) Model, 286
Transmission Line, 90, 163
Z-Domain Filter, 92, 299
Device Model Description (.MODEL), 723
Device Models, 89 to 93, 119
DEX, 1227
Dialogue
of Pole-Zero Post-processor, 1122
DICPRIO option, 952
Differential Comparator Macromodel, 97, 381
Differential Operational Amplifier Macromodel
Linear, 384
Linear 1-pole, 387
Linear 2-pole, 391
Differential Output Level Detector Macromodel, 99, 433
Differentiated Accuracy System, 301, 302, 899
Differentiator Macromodel, 99, 440
Parameters, 440
Diffusion Resistor Model, 154
Parameters, 154
Digital Circuit Conditions
Initialization of (.INIT), 688
Digital Gate with Double Input Macromodel
Digital Gate with Multiple Input Macromodel, 461
Digital Gate with Triple Input Macromodel, 459
Digital Macromodels, 100, 447
Digital Model Definition
.MODEL ... LOGIC, 449
.MODLOGIC, 727
DIGITAL option, 1017
digital states
test vectors, 922
Diode Models, 225, 228
.SENS, 863
Berkeley Level 1, 229

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Fowler-Nordheim Model (Eldo Level 3), 230
Modified Berkeley Level 1 (Eldo Level 2), 229
Disable Flat Netlist Model (.DISFLAT), 613
DISPLAY_CARLO option, 999
DISTO (extract function), 648
Distribution Sharing
(.LOTGROUP), 701

Divider Macromodel, 100, 444
Parameters, 444
DMAX (Maximum value), 79
DMIN (Minimum value), 79
Documentation Conventions, 38
DOTNODE option, 952
Double Input AND Gate Macromodel, 100, 457, 459, 461
Double Input Digital Gates
Double Input NAND Gate Macromodel, 100, 457, 459, 461
Double Input NOR Gate Macromodel, 100, 457, 459, 461
Double Input OR Gate Macromodel, 100, 457, 459, 461
Double Input XOR Gate Macromodel, 100, 457, 459, 461
DPTRAN option, 1017
DSCGLOB option, 976
DSP computation (.DSP), 615
DSPF files, 617
DSPF_LEVEL option, 976
DTC (extract function), 647
DUMP_FILE_LIST option, 1011
DVDT option, 963

- E -

Effects of Error Messages, 1411
Efficient Usage of Eldo, 302, 854, 857, 899, 926, 963
EKV MOS Model (Level =EKV or 44), 271
EKV3 MOS Model (Level =EKV3 or 61), 286 Eldo

An Introduction, 31
chi2cir utility, 1495
Control Language, 69
convert .chi to .cir, 1495

Efficient Usage, 1061
Efficient Usage of, 302, 854, 857, 899, 926, 963
Encryption, 1499
Getting Started, 31
Input and Output Files, 32
Running from the Command Line, 41
Running of, 34
Speed and Accuracy, 1061
Syntax, 70
Temperature Handling, 88
Utilities, 1495
eldo.ini, 60
ELDOMOS option, 984
EMPTY_MCHISTO option, 1000
Encryption, 1499
End Eldo Library Variant Description (.ENDL), 632

End Eldo Netlist (.END), 631
End Eldo Subcircuit Description (.ENDS), 633
END test vector file keyword, 921
endhref, 963
ENGNOT option, 995
Enhanced Berkeley SPICE Level 2 (Level 17) MOSFET Model, 270
EPS option, 302, 484, 899, 964, 1457
EPSO option, 1021
ERR0DIV0 option, 952
Error Messages, 1411, 1412
Classification of, 1411
Effects, 1411
Global, 1412
Miscellaneous, 1432
Related to Amodels, 1431
Related to Commands, 1423
Related to Models, 1430
Related to Nodes, 1415
Related to Objects, 1416
Related to Subcircuits, 1432
Euler Backward Integrator, 517
Euler Forward Integrator, 515
EVAL (extract function), 648
Examples, 1459
4-bit Adder, 1461
5th Order Elliptic SC Low Pass Filter, 1469

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Active RC Band Pass Filter, 1474
Cascade of Inverters, 35
Charge Control in MOS Models 4 and 6, 1472
CMOS Operational Amplifier (Closed Loop), 1467
CMOS Operational Amplifier (Open Loop), 1465
Post-Processing Library, 1260
SC—Schmitt Trigger, 1460
Second Order Delta Sigma Modulator, 1477
Exclusive-OR Gate, 456
EXP (Exponent of value), 78
Exponential Function, 95, 325
Exponential Pulse With Bit Pattern Function (EBIT), 95
Expressions in Eldo, 84
EXTCGS option, 1000
EXTERR option, 952
EXTFILE option, 1000
EXTMKSA option, 1000
EXTMOD_GENWAVE option, 1000
Extract accessor functions, 643
Extract Mode (.EXTMOD), 636
Extract Waveform Characteristics
(.EXTRACT), 637

Extract Waveform Characteristics (.MEAS), 717
EXTRACT_EVAL_FINAL option, 1000
EXTRACT_VECT_AXIS option, 1001
EZwave, 47

- F -

FALL_TIME option, 977
FALLING (extract function), 649
FAS
Macromodel Usage, 380
FASTRLC option, 964
Feedback Loop
Insertion of (.LOOP), 699
ffcv utility, 1497
FFT
post-processor options (.OPTFOUR), 764
select waveform (.FOUR), 673

5th Order Elliptic SC Low Pass Filter Example, 1469
files
test vector, 918 to 924
Filter Data Driven Simulations (.FILTER), 669
First Line in Eldo, 70
FLICKER_NOISE option, 994
FLOOR (Value rounded down to integer), 79
FLUXTOL option, 964
FNLEV option, 985
FNS Model, 1125
4-bit Adder Example, 1461
Fowler-Nordheim Diode Model (Eldo Level 3), 230

Parameters, 230
FREQSMP option, 964
Frequency computation (.DSPMOD), 625
Frequency Limit
for Pole-Zero Post-processing, 1123
FS_PARTITION_DEBUG option, 1020
FS_PARTITIONING option, 1020
FS_SOLVE_AMS_NODES option, 1020
FSDB, 47
FSDB option, 1011
FT option, 965
Functions \& Operators
see Arithmetic Functions \& Operators

- G -

GA, 821
GAC, 820
Gain Extract
see Two-port Gain Extract
GAM, 821
GASM, 821
GAUM, 822
GEAR option, 1016
Generalized Re-run Facility, 549
GENK option, 986
Getting Started with Eldo, 31
Global
Declarations (.PARAM), 778
Error Messages, 1412
Node Allocation (.GLOBAL), 676
Warning Messages, 1436

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

GMIN option, 985
GMIN_BJT_SPICE option, 985
GMINDC option, 985
GNODE option, 1016
GP, 822
GPC, 821
GRAMP option, 985
Grounded Capacitors Information, 86
GSHUNT option, 1018

## - H -

HACC option, 965, 1069
Hand Selection
in Pole-Zero Post-processing, 1124
HICUM Model
Parameters, 240, 243
HIER_SCALE option, 986
Hierarchical Nodes
Monitoring of, 817
Hierarchy Separator
changing (.HIER), 680
High Voltage Cascade Tutorial, 1359
High-rate Particle Detector Circuit, 1026
HIGHVOLTAGE option, 977
HIGHVTH option, 978
HiSIM (Eldo Level 66) MOSFET Model, 289
HiSIM-LDMOS (Eldo Level 73) MOSFET
Model, 293
HISTLIM option, 1001
Histogram computation (.DSPMOD), 625
HMAX option, 965
HMIN option, 965
How to Run Eldo, 34
href
ica
//eldo_ur\#99EPS, 963
HRISEFALL option, 965
HSPICE Compatibility, 1373 to 1383
— I -
IBIS_SEARCH_PATH option, 986
ICDC option, 978
ICDEV option, 978, 979
Ideal Operational Amplifier Macromodel, 102, 492

Ideal Single-Pole Multiple-Throw Switch Macromodel, 407
Parameters, 407
IDT (Integral of value), 79
IEM, 1099 to 1119
Accuracy
RELTOL, 970
IEM option, 1016
IKF2 option, 994
IMAG (Imaginary part of complex number), 79
Impedance parameters, 1041
INCLIB option, 965
Include a File in an Input Netlist (.INCLUDE), 685
Independent Current Source, 317
.LOOP, 699
.SENS, 863
Independent Sources, 307
Independent Voltage Source, 310
.LOOP, 699
.SENS, 863
Multi-tone, 311, 318
Inductor Model, 90, 140, 145
Parameters, 145
INFODEV option, 1012
INFOMC option, 1001
INFOMOD option, 1012
INGOLD option, 995
Initial DC Analysis Conditions (.GUESS), 677
Initial Digital Circuit Conditions (.INIT), 688
Initial Transient Analysis Conditions
(.FORCE), 672

Initial Transient Analysis Conditions (.IC), 682
Initialization file, 60
INOISE, 799
Input and Output Files for Eldo, 32
Input from a Prior Simulation (.CHRSIM), 569
INPUT option, 1001
Insert
a Feedback Loop (.LOOP), 699
a Model or Subcircuit File, 544
Circuit Information from a Library File
see Library Files-Insertion of (.LIB)
INT (Integer of value), 78
INTEG (extract function), 649

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Integral Equation Method
see IEM
Integrator Macromodel, 99, 442
Parameters, 442
Interactive Mode, 1483
INTERP option, 978
Interruption of a Simulation, 1084
Inverter Macromodel, 100, 454
Inverting Switched Capacitor Macromodel, 102, 495
Equations, 496
Parameters, 496
Iteration Techniques
Newton Raphson, 302, 899, 1017
One Step Relaxation, 1017
ITL1 option, 965
ITL3 option, 965
ITL4 option, 966
ITL6 option, 966
ITL7 option, 966
ITL8 option, 966
ITOL option, 966
ITRPRT option, 1012
— J -
JFET Model, 246
Parameters, 246
JTHNOISE option, 994
JUNCAP Level 8 Diode Model
Parameters, 230
Junction Diode Models, 225, 228
Berkeley Level 1, 229
STMicroelectronics, 1510
Junction Field Effect Transistor (JFET) Model, 92, 244
JWDB, 33, 47
JWDB option, 1012

- K -

KEEP_DSPF_NODE option, 1002
KEEPDANGLING option, 952
KEEPSHORTED option, 953
Keywords, reserved, 72
KFACTOR, 818
KFACTOR (extract function), 649
KLIM option, 986

KWSCALE option, 991
— L —
LCAPOP option, 1002
LDI Definition, 491
LDI Phase Control Euler Backward Integrator, 518
LDI Phase Control Euler Forward Integrator, 516
LDI Phase Control Non-inverting Integrator, 514
LDTL
see Lossy Transmission Line
Level Detector Macromodel, 433
Differential Output Level Detector, 433
Parameters, 433
Single Output Level Detector, 433
LIBINC option, 966
Library Files
Insertion of (.LIB), 692
Library variant Description Termination (.ENDL), 632

LICN option, 979
LIMIT, 79
LIMNWRMOS option, 966
LIMPROBE option, 838, 1002
line continuation
test vector files, not available for, 920
line length, maximum
test vector files, 920
Linear Dependent Sources, 308
Linear Magnetic Core Macromodel, 101, 476
LIST option, 1003
Load DSPF File (.DSPF_INCLUDE), 617
Loading Large Databases, 45
LOCAL_MAX (extract function), 649
LOCAL_MIN (extract function), 650
LOCAL_NOWARN option, 995
LOG (Neperian log of value), 78
LOG10 (Decimal log of value), 78
Logarithmic Amplifier Macromodel, 99, 436
Parameters, 436
Loop Stability Analysis (.LSTB), 703
LOOPV0 option, 953
Lossy Transmission Line Model, 165
LDTL, 165

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Level 1, 165
Level 2, 167
Level 3, 169
Level 4, 170
U Model, 91, 192
W Model, 91, 181
LOT \& DEV Variation Specification on Model Parameters (Monte Carlo) (.MCMOD), 715
Low Pass Filter Tutorial, 1353
LOWVOLTAGE option, 977
LOWVTH option, 978
LSC
see Two-port Stability Circles
LSF, 735
LVLTIM option, 966
LVS_IGNORE_VARIABLE option, 979

- M —

M53 option, 979
MACMOD option, 954
Macro Definition (.DEFMAC), 601
Macromodel Description
2-Input Digital Gates, 100
3-Input Digital Gates, 100, 459
A-D Converter, 101, 463
Adder, 100, 444
Adder, Subtractor, Multiplier, Divider, 100, 444
Amplitude Modulator, 98, 417
Anti-logarithmic Amplifier, 99, 438
Bi-linear Switched Capacitor, 102, 508
Comparator, 97, 381
Current Controlled Switch, 98, 404
Current Limiter, 399
D-A Converter, 101, 465
Delay, 98, 100, 394, 453
Differential Comparator, 97, 381
Differential Operational Amplifier
Linear, 97, 384
Linear 1-pole, 97, 387
Linear 2-pole, 98, 391
Differential Output Level Detector, 99, 433
Differentiator, 99, 440
Divider, 100, 444
Double Input Digital Gates, 100

Exclusive-OR Gate, 100, 456
Ideal Operational Amplifier, 102, 492
Ideal Single-Pole Multiple-Throw Switch, 407
Ideal Transformer, 101, 480
Integrator, 99, 442
Inverter, 100, 454
Inverting Switched Capacitor, 102, 495
Level Detector, 99, 433
Differential Output, 99, 433
Single Output, 99, 433
Linear Magnetic Core, 101, 476
Logarithmic Amplifier, 99, 436
Magnetic Air Gap, 101, 477
Mixed Signal Macromodels, 462
Multiple Input Digital Gates, 100, 461
Multiplier, 100, 444
Non-inverting Switched Capacitor, 102, 498
Non-linear Magnetic Core 1, 101, 470
Non-linear Magnetic Core 2, 101, 473
Operational Amplifier
Linear, 97, 384
Linear 1-pole, 97, 387
Linear 2-pole, 97, 391
Switched Capacitor, 483
Operational Amplifier (SC), 101
Parallel Switched Capacitor, 102, 501
Peak Detector, 99, 430
Pulse Amplitude Modulator, 99, 419
Pulse Width Modulator, 99, 425
Sample and Hold, 99, 421
Saturating Resistor, 98, 395
Sawtooth Waveform Generator, 98, 413
Serial Switched Capacitor, 102, 503
Serial-parallel Switched Capacitor, 102, 505
Single Output Level Detector, 99, 433
Staircase Waveform Generator, 98, 411
Subtractor, 100, 444
Switch (SC), 102, 488
Track and Hold, 99, 423
Transformer Winding, 101, 468
Transformer with Variable Number of Windings, 101, 478

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Triangle Waveform Generator, 98, 415
Triangular to Sine Wave Converter, 98, 409
Triple Input Digital Gates, 100, 459
Unswitched Capacitor, 102, 510
Voltage Controlled Oscillator (VCO), 99, 428
Voltage Controlled Switch, 98, 401
Voltage Limiter, 98, 397
Macromodels, 379 to 445, 481 to 511
Analog, 97 to 100, 379
Digital, 100, 447
General Notes on the Use of, 491
Magnetic, 101, 467
Mixed, 462
Mixed Signal, 101
Switched Capacitor, 101, 481
Magnetic Air Gap Macromodel, 101, 477
Magnetic Macromodels, 101, 467
MAGNITUDE (Magnitude of complex number), 79
Mapping Model and Subcircuit Names
(.MALIAS), 704

Mapping Model Names (.DEFMOD), 603
Matrix Information in Eldo, 87
MAX (extract function), 650, 651, 657, 658
MAX (Maximum value), 79
max, test vector file keyword, 921
MAX_DSPF_PLOT option, 1003
MAXADS option, 987
MAXL option, 987
MAXNODEORD option, 1021
MAXNODES option, 967
MAXORD option, 1016
MAXSTEP option, 967
MAXTOTWARN option, 995
MAXTRAN option, 967
MAXV option, 967
MAXW option, 987
MAXWARN option, 996
MC_IGNORE_BINNING option, 980
MEAN (extract function), 651
MEAS_TARGWHEN option, 954
MEASFILE option, 1003
MERCKEL MOSFET Models (Levels 4-6), 266

Parameters, 266
MESFET Model, 92, 248
Parameters, 248
Metal Field Effect Transistor (MESFET)
Model, 92, 248
Metal Oxide Field Effect Transistor (MOSFET) Model, 92
METHOD=GEAR option, 1016
Mextram 503.2 Model, 237
Mextram 504 Model, 240
Microstrip Models, 197 to 224
90-degree Microstrip Bend, 204, 207, 210
Cylindrical Via Hole in Microstrip, 215
MBEND, 201
MBEND2, 204
MBEND3, 207
MCORN, 210
Microstrip Bend, 201
Microstrip Step in Width (MSTEP), 213
Microstrip T Junction, 198
MTEE, 198
Stripline Step in Width (SSTEP), 223
Stripline T Junction (STEE), 221
Unmitered Stripline Bend (SBEND), 218
VIA2, 215
MIN (extract function), 652
MIN (Minimum value), 79
MINADS option, 987
MINL option, 987
MINPDS option, 987
MINRACC option, 987
MINRESISTANCE option, 987
MINRVAL option, 987
MINW option, 987
Miscellaneous
Error Messages, 1432
Warning Messages, 1450
Mixed Signal Macromodels, 101, 462
MIXEDSTEP option, 1019
MMSMOOTH option, 980
MMSMOOTHEPS option, 981
MNUMER option, 988
MOD (Modulo value), 80
MOD4PINS option, 988
Model

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Error Messages, 1430
File Insertion (.ADDLIB), 544
Names in Eldo, 73
Warning Messages, 1448
Modella Model, 241
Models
Berkeley BSIM3v2 (Level 47), 272
Berkeley BSIM3v3 (Level 53), 273
Berkeley BSIM4 (Level 60), 284
Berkeley BSIMSOI3 (Level 55), 277
Berkeley BSIMSOI3 (Level 56), 279
Berkeley BSIMSOI4.0 (Level 72), 292
Berkeley SPICE BSIM1, 267
Berkeley SPICE BSIM2, 268
Bipolar Junction Transistor (BJT), 235, 237
BJT, 92
BTA HVMOS (Level =101), 295
Capacitor, 90, 137
Comparator, 382
Coupled Inductor, 90, 147
Diffusion Resistor, 90, 154
Diode, 228
EKV MOS (Level=EKV or 44), 271
EKV3 MOS (Level=EKV3 or 61), 286
Enhanced Berkeley SPICE Level 2 (Level 17), 270

HiSIM MOSFET (Eldo Level 66), 289
HiSIM-LDMOS MOSFET (Eldo Level 73), 293

Inductor, 90, 145
JFET, 92
Junction Diode, 92, 228
Junction Field Effect Transistor (JFET), 246
Lossy Transmission Line, 91, 165
Level 1, 165
Level 2, 167
Level 3, 169
Level 4, 170
U Model, 91, 192
W Model, 91, 181
MESFET, 92, 248
Microstrip, 197 to 224
Microstrip Bend, 91
Miltered, 91

Optimally miltered, 91
Unmiltered, 91
Microstrip T junction, 91
Modified Berkeley Level 2 (Level 12), 269
Modified Berkeley Level 3 (Level 13), 270
Modified Lattin-Jenkins Grove (Level 16), 270
MOSFET, 92, 249
MOSVAR MOSFET (Eldo Level 74), 294
Motorola SSIM (Level 54 or SSIM), 276
Philips MOS 11 Level 1100 (Eldo Level 65 or MOSP11), 288
Philips MOS 11 Level 1100 (Eldo Level 69), 290

Philips MOS 11 Level 1101 (Eldo Level 63 or MOSP11), 286
Philips MOS 20 Level 2001 (Eldo Level 71), 292

Philips MOS 9 (Level 59 or MOSP9), 283
Philips PSP (Level 70), 291
PSP103 (Level 75), 295
RC Wire, 90, 150
Resistor, 89, 128
S-Domain Filter, 92, 297
Semiconductor Resistor, 90, 156
SP MOSFET (Eldo Level 67), 290
STMicroelectronics, 1509
Subcircuit Instance, 93, 301
TFT Amorphous-Si (Level 64), 287
TFT Polysilicon (Level 62), 286
Transmission Line, 90, 163
Z-Domain Filter, 92, 299
Modified Berkeley Level 1 (Eldo Level 2) Diode Model, 229
Parameters, 229
Modified Berkeley SPICE Level 2 (Level 12) MOSFET Model, 269
Parameters, 269
Modified Berkeley SPICE Level 3 (Level 13) MOSFET Model, 270
Parameters, 270
Modified Gummel-Poon Parameters, 237, 238
MODMONTE option, 988
MODPAR (extract function), 652
MODWL option, 988

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

MODWLDOT option, 988
Monitor Simulation Steps (.MONITOR), 728
Monitoring of Hierarchical Nodes, 817
Monte Carlo Analysis (.MC), 706
Capacitor Model, 137
Examples, 1363
Inductor Model, 145
Multiple Runs, 712
MOSFET Models, 249
Berkeley BSIM3v2 (Level 47), 272
Berkeley BSIM3v3 (Level 53), 273
Berkeley BSIM4 (Level 60), 284
Berkeley BSIMSOI3 (Level 55), 277
Berkeley BSIMSOI3 (Level 56), 279
Berkeley BSIMSOI4.0 (Level 72), 292
Berkeley SPICE BSIM1, 267
Berkeley SPICE BSIM2, 268
Berkeley SPICE Levels 1-3, 265
EKV MOS (Level =EKV or 44), 271
EKV3 MOS (Level =EKV3 or 61), 286
Enhanced Berkeley SPICE Level 2 (Level 17), 270

HiSIM (Eldo Level 66), 289
HiSIM-LDMOS (Eldo Level 73), 293
HVMOS (Level = 101), 295
MERCKEL MOS Levels 4-6, 266
Modified Berkeley SPICE Level 2 (Level 12), 269

Modified Berkeley SPICE Level 3 (Level 13), 270

Modified Lattin-Jenkins Grove (Level 16), 270
MOSVAR (Eldo Level 74), 294
Motorola SSIM (Level 54 or SSIM), 276
Philips MOS 11 Level 1100 (Eldo Level 65 or MOSP11), 288
Philips MOS 11 Level 1100 (Eldo Level 69), 290

Philips MOS 11 Level 1101 (Eldo Level 63 or MOSP11), 286
Philips MOS 20 Level 2001 (Eldo Level 71), 292

Philips MOS 9 (Level 59 or MOSP9), 283
Philips PSP (Level 70), 291
PSP103 (Level 75), 295

SP (Eldo Level 67), 290
STMicroelectronics, 1511
TFT Amorphous-Si (Level 64), 287
TFT Polysilicon (Level 62), 286
UDMP, 255
MOSVAR (Eldo Level 74) MOSFET Model, 294
MOTOROLA
option, 950
SSIM (Level 54 or SSIM) MOSFET Model, 276
MSGBIAS option, 996
MSGNODE option, 996
MTHREAD option, 954
Multiple Affectation of Parameters
.PARAM -compat flag, 786
Multiple Input AND Gate Macromodel, 100
Multiple Input Digital Gates, 100, 461
Multiple Input NAND Gate Macromodel, 100
Multiple Input NOR Gate Macromodel, 100
Multiple Input OR Gate Macromodel, 100
Multiplier Macromodel, 100, 444
Parameters, 444
Multi-tone, 311, 318
$-\mathbf{N}$ -
NAND Gate
see Double, Triple and Multiple Input Digital Gates
Nested Output Requests, 817
Netlist Protection
.PROTECT, 850
.UNPROTECT, 925
Netlist Termination (.END), 631
NETSIZE option, 967
Network Analysis
(.NET), 111, 740

NEWACCT option, 1003
Newton Block Information in Eldo, 87
NEWTON option, 1016
Newton Raphson
Accuracy
RELTOL, 970
NGATEDEF option, 989
NGTOL option, 967

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

NMAXSIZE option, 967
NO_FS_VA option, 1020
NOACDERFUNC option, 989
NOACT0 option, 955
NOAEX option, 1012
NOALTINCEX option, 955
NOASCII option, 1004
NOASCIIPLOT option, 1004
NOAUTOCTYPE option, 989
NOBOUND_PHASE option, 1004
NOBSLASHCONT option, 955, 1381
NOCATMX option, 989
NOCKRSTSAVE option, 1012
NOCMPUNIX option, 955
NOCONVASSIST option, 968
NOCOU option, 1012
Nodal
Error Messages, 1415
Warning Messages, 1439
NODCINFOTAB option, 1004
NODCPART option, 1017
NODCPOWNEG option, 968
Node and Element Information in Eldo, 86
Node Names
inside Subcircuits, 902
NODE option, 1004
NODEFNEWTON option, 1016
NODEFRMSNTR option, 1004
Nodes
Global (.GLOBAL), 676
Node Name conventions in Eldo, 72
Node Names inside Subcircuits, 73
NOELDOSWITCH option, 1021
NOERR_XPINSMISMATCH option, 956
NOEXTRACTCOMPLEX option, 1004
NOFNSIEM option, 1022
NOICNODE option, 981
NOIICXNAME option, 1012
NOINIT option, 1022
Noise
Function, 95, 327
Performance Analysis, 1027
Noise Analysis
.NOISE, 744
.PRINT, 805, 813

AC (.OPTNOISE), 772
NONOISE, 125, 226, 233, 245, 251, 302, 314, 321
Transient, 1023
Noise Circles
see Two-port Noise Circles
Noise Function, 95
Noise Parameters
see Two-port Noise Parameters
Noise Source Correlation
.NOISE_CORREL, 746
Noise Table
Function, 330
NOJWDB option, 1012
NOKEYWPARAMSST option, 956
NOKWSCALE option, 991
NOLAT option, 968
NOLICN option, 981
NOLTEDISC option, 981
NOMEMSTP option, 981
NOMOD option, 1005
NOMODWL option, 989
Non-inverting Amplifier Tutorial, 1363
Non-inverting Integrator, 513
Non-inverting Switched Capacitor Macromodel, 102, 498
Equations, 499
Parameters, 498
Non-linear Dependent Sources, 308
Non-linear Magnetic Core 1 Macromodel, 101, 470
Non-linear Magnetic Core 2 Macromodel, 101, 473
NONOISE option, 125, 226, 233, 245, 251, 302, 314, 321, 994
NONWRMOS option, 968
NOOP option, 1005
NOPAGE option, 1005
NOPROBEOP option, 1012
NOQTRUNC option, 968
NOR Gate
see Double, Triple and Multiple Input
Digital Gates
NORMOS option, 1017
NOSETBUSEXPAND option, 956

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

NOSIZECHK option, 1005
NOSSTKEYWORD option, 956
NOSTATP option, 1008
NOSWITCH option, 968
NOTRC option, 1005
NOTRCLIB option, 1005
NOVATOPOCHK option, 981
NOWARN option, 996
NOWAVECOMPLEX option, 1005
NOXTABNOISE option, 1005
NOZSINXX option, 956
NSAFILE_FORMAT option, 1012
NUMDGT option, 996
NWRMOS option, 989

- O -

Object
Error Messages, 1416
Warning Messages, 1440
ONGRID, 80
ONOISE, 799
OPALLDC option, 1006
Operating Point
Calculation of, 1079
DC, 967, 973
Operational Amplifier (SC) Macromodel, 101, 483
Equations (Single Stage), 485
Equations (Two Stage), 486
Equivalent Circuit, 485
Parameters, 487
Operational Amplifier Macromodel
Linear, 97, 384
Characteristics, 385
Parameters, 384
Linear 1-pole, 97, 387
Application Area, 389
Characteristics, 388
Parameters, 387
Linear 2-pole, 97, 391
Characteristics, 392
Parameters, 391
Operator Precedence, 82
Operators, 82
Operators in Eldo, 82
OPMODE (extract function), 652

OPMODE (plot function), 801
OPSELDO_ABSTRACT option, 1008
OPSELDO_DETAIL option, 1008
OPSELDO_DISPLAY_GOALFITTING
option, 1008
OPSELDO_FORCE_GOALFITTING option, 1009
OPSELDO_JWDB_RUN option, 1009
OPSELDO_NETLIST option, 1009
OPSELDO_NO_DUPLICATE option, 1010
OPSELDO_NOGOALFITTING option, 1010
OPSELDO_OUTER option, 1010
OPSELDO_OUTPUT option, 1010
Optimization
.OBJECTIVE, 754
.OPTIMIZE, 770
.PARAMOPT, 789
Optimizer, 1127
.OBJECTIVE, 754
.OPTIMIZE, 770
.PARAMOPT, 789
Overview, 1127, 1227
Options
CADENCE Compatibility
SDA, 949
WSF, 949
WSFASCII, 949
File Generation
AEX, 1010
ALIGNEXT, 1011
ASCII, 1011
COU, 1011
CSDF, 1011
DUMP_FILE_LIST, 1011
FSDB, 1011
INFODEV, 1012
INFOMOD, 1012
ITRPRT, 1012
JWDB, 1012
NOAEX, 1012
NOCKRSTSAVE, 1012
NOCOU, 1012
NOIICXNAME, 1012
NOJWDB, 1012
NOPROBEOP, 1012

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

NSAFILE_FORMAT, 1012
OUT_ABSTOL, 1013
OUT_REDUCE, 1013
OUT_RELTOL, 1013
PROBE, 1013
PROBEOP, 1013
PROBEOP2, 1014
PROBEOPX, 1014
PSF, 1014
PSF_ALL_FILES, 1015
PSF_FULLNAME, 1015
PSF_NODEVICE_NOISE, 1014
PSF_SCALARDC, 1014
PSF_VERSION, 1014
PSF_WRITE_ALL, 1015
PSFASCII, 1015
SAVETIME, 1015
WDF, 1015
Mathematical Algorithm
ANALOG, 1016
BE, 1016
BLOCKS, 1016
CSHUNT, 1017
DCPART, 1017
DIGITAL, 1017
GEAR, 1016
GNODE, 1016
GSHUNT, 1018
IEM, 1016
MAXORD, 1016
METHOD, 1016
NEWTON, 1016
NODCPART, 1017
NODEFNEWTON, 1016
NORMOS, 1017
OPTRAN, 1017
OSR, 1017
PSTRAN, 1017
SMOOTH, 1015
TRAP, 1015
Miscellaneous Simulation Control
AIDSTP, 963
AMMETER, 974
AUTOSTOP, 974
AUTOSTOPMODULO, 975

CARLO_GAUSS, 975
CPTIME, 975
DEFAULTFALLTIME, 975
DEFAULTRISETIME, 975
DEFPTNOM, 976
DSCGLOB, 976
DSPF_LEVEL, 976
FALL_TIME, 977
HIGHVOLTAGE, 977
HIGHVTH, 978
ICDC, 978
ICDEV, 978, 979
INTERP, 978
LICN, 979
LOWVOLTAGE, 977
LOWVTH, 978
M53, 979
MMSMOOTH, 980
MMSMOOTHEPS, 981
NOICNODE, 981
NOLICN, 981
NOLTEDISC, 981
NOMEMSTP, 981
NOVATOPOCHK, 981
PARAMOPT_NOINITIAL, 981
RANDMC, 982
RGND, 982
RGNDI, 982
RISE_TIME, 977
SIGTAIL, 982
STATISTICAL, 982
TEMP_UNIT, 982
TNOM, 983
TPIEEE, 983
ULOGIC, 983
ZOOMTIME, 983
Mixed-Mode
D2DMVL9BIT, 1018
DEFA2D, 1018
DEFCONVMSG, 1018
DEFD2A, 1018
FS_PARTITION_DEBUG, 1020
FS_PARTITIONING, 1020
FS_SOLVE_AMS_NODES, 1020
MIXEDSTEP, 1019

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

NO_FS_VA, 1020
PARTGATE_AMS_ALL, 1019
PARTVDD, 1019
PARTVDD_AMS_ALL, 1019
Model Control
ACDERFUNC, 983
ACM, 983
ASPEC, 983
BSIM3VER, 984
DEFAD, 984
DEFAS, 984
DEFL, 984
DEFNRD, 984
DEFNRS, 984
DEFPD, 984
DEFPS, 984
DEFW, 984
ELDOMOS, 984
FNLEV, 985
GENK, 986
GMIN, 985
GMIN_BJT_SPICE, 985
GMINDC, 985
GRAMP, 985
HIER_SCALE, 986
IBIS_SEARCH_PATH, 986
KLIM, 986
KWSCALE, 991
LVS_IGNORE_VARIABLE, 979
MACMOD, 954
MAXADS, 987
MAXL, 987
MAXPDS, 987
MAXW, 987
MINADS, 987
MINL, 987
MINPDS, 987
MINRACC, 987
MINRESISTANCE, 987
MINRVAL, 987
MINW, 987
MNUMER, 988
MOD4PINS, 988
MODMONTE, 988
MODWL, 988

MODWLDOT, 988
NGATEDEF, 989
NOACDERFUNC, 989
NOAUTOCTYPE, 989
NOCATMX, 989
NOKWSCALE, 991
NOMODWL, 989
NWRMOS, 989
PGATEDEF, 989
RAILINDUCTANCE, 989
RAILRESISTANCE, 989
REDUCE, 990
RESNW, 990
RMMINRVAL, 990
RMOS, 990
SCALE, 991
SCALEBSIM, 991
SCALM, 991
SHRINK_FACTOR, 992
SOIBACK, 992
SPMODLEV, 992
TMAX, 992
TMIN, 992
USE_LOCATION_MAP, 961
USEDEFAP, 992
WARNMAXV, 992, 993
WL, 993
YMFACT, 993
Netlist Parser Control
ACCSEMICOL, 950
ALTER_ADDSTEP, 951
ALTERELDO, 951
ALTINC, 951
BSLASHCONT, 951
CHECKDUPL, 951
CKDCPATH, 951, 1380
COMPEXUP, 951, 1381
CONTINUE_INCLUDE, 952
DICPRIO, 952
DOTNODE, 952
ERR0DIV0, 952
EXTERR, 952
KEEPDANGLING, 952
KEEPSHORTED, 953
LOOPV0, 953

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

MEAS_TARGWHEN, 954
MTHREAD, 954
NOACT0, 955
NOALTINCEX, 955
NOBSLASHCONT, 955, 1381
NOCMPUNIX, 955
NOERR_XPINSMISMATCH, 956
NOKEYPARAMSST, 956
NOSETBUSEXPAND, 956
NOSSTKEYWORD, 956
NOZSINXX, 956
PARAM_BEFORE_USE, 956
PARHIER, 956
PEVFLY, 959
POWNEG0, 959
RMV0, 960
SLASHCONT, 960
STOPONFIRSTERROR, 960
STRICT, 960
SUBALEV, 961
SUBFLAGPAR, 961
USEFIRSTDEF, 962
USETHREAD, 962
VOLTAGE_LOOP_SEVERITY, 962
WARN2ERR, 962
XBYNAME, 962
Noise Analysis
FLICKER_NOISE, 994
IKF2, 994
NONOISE, 994
THERMAL_NOISE, 994
UTHNOISE, 994
Optimizer Output Control
OPSELDO_ABSTRACT, 1008
OPSELDO_DETAIL, 1008
OPSELDO_DISPLAY_GOALFITTIN G, 1008
OPSELDO_FORCE_GOALFITTING, 1009
OPSELDO_JWDB_RUN, 1009
OPSELDO_NETLIST, 1009
OPSELDO_NO_DUPLICATE, 1010
OPSELDO_NOGOALFITTING, 1010
OPSELDO_OUTER, 1010
OPSELDO_OUTPUT, 1010

RESET_MULTIPLE_RUN, 1010
Other
CTEPREC, 1021
DCLOG, 1021
EPSO, 1021
MAXNODEORD, 1021
NOFNSIEM, 1022
NOINIT, 1022
NOOP, 1005
SEARCH, 1022
VAMAXEXP, 1022
ZCHAR, 1022
Simulation Accuracy \& Efficiency
ABSTOL, 963
ABSVAR, 963
ADJSTEPTRAN, 963
CAPANW, 963
CHGTOL, 963
DVDT, 963
EPS, 964
FASTRLC, 964
FLUXTOL, 964
FREQSMP, 964
FT, 965
HACC, 965
HMAX, 965
HMIN, 965
HRISEFALL, 965
INCLIB, 965
ITL1, 965, 968
ITL3, 965
ITL4, 966
ITL6, 966
ITL7, 966
ITL8, 966
ITOL, 966
LIBINC, 966
LIMNWRMOS, 966
LVLTIM, 966
MAXNODES, 967
MAXSTEP, 967
MAXTRAN, 967
MAXV, 967
NETSIZE, 967
NGTOL, 967

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

NMAXSIZE, 967
NOCONVASSIST, 968
NODCPOWNEG, 968
NOLAT, 968
NONWRMOS, 968
NOQTRUNC, 968
NOSWITCH, 968
PCS, 968
PCSPERIOD, 969
PCSSIZE, 969
PIVCHECK, 969
PIVREL, 969
PIVTOL, 970
PSOSC, 970
QTRUNC, 970
RATPRINT, 970
RELTOL, 970
RELTRUNC, 971
RELVAR, 971
SAMPLE, 971
SPLITC, 971
STARTSMP, 971
STEP, 971
TIMESMP, 972
TRTOL, 972
TUNING, 972
UNBOUND, 973
VMAX, 973
VMIN, 973
VNTOL, 974
XA, 974
Simulation Display Control
ENGNOT, 995
INGOLD, 995
LOCAL_NOWARN, 995
MAXTOTWARN, 995
MAXWARN, 996
MSGBIAS, 996
MSGNODE, 996
NOTRCLIB, 1005
NOWARN, 996
NUMDGT, 996
PRINTFILE_FREQ_STEP, 1007
PRINTFILE_STEP, 1007
PRINTFILE_TIME_STEP, 1007

PRINTLG, 997
STAT, 1008
VERBOSE, 997
WARN, 997
WBULK, 997
Simulation Output Control
ACOUT, 997
ALTER_NOMINAL_TEXT, 998
ALTER_SUFFIX, 998
ASCII, 998
ASCIIPLOT, 998
BLK_SIZE, 998
CAPTAB, 998
COLLAPSE_DSPF_OUTPUT, 999
CONTINUOUS_FFT, 999
DEFRMSNTR, 999
DISPLAY_CARLO, 999
EMPTY_MCHISTO, 1000
EXTCGS, 1000
EXTFILE, 1000
EXTMKSA, 1000
EXTMOD_GENWAVE, 1000
EXTRACT_EVAL_FINAL, 1000
EXTRACT_VECT_AXIS, 1001
HISTLIM, 1001
INFOMC, 1001
INPUT, 1001
KEEP_DSPF_NODE, 1002
LCAPOP, 1002
LIMPROBE, 1002
LIST, 1003
MAX_CHECKBUS, 1003
MAX_DSPF_PLOT, 1003
MEASFILE, 1003
NEWACCT, 1003
NOASCII, 1004
NOASCIIPLOT, 1004
NOBOUND_PHASE, 1004
NODCINFOTAB, 1004
NODE, 1004
NODEFRMSNTR, 1004
NOEXTRACTCOMPLEX, 1004
NOMOD, 1005
NOPAGE, 1005
NOSIZECHK, 1005

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

NOSTATP, 1008
NOTRC, 1005
NOWAVECOMPLEX, 1005
NOXTABNOISE, 1005
OPALLDC, 1006
OPTYP, 1006
OUT_RESOL, 1006
OUT_SMP, 1006
OUT_STEP, 1006
PARAMETRIC_ACTRAN, 1006
POST, 1006
POST_DOUBLE, 1007
SIMUDIV, 1007
STAT, 1007
TEMPCOUK, 1008
TIMEDIV, 1008
VBCSAT, 1008
VXPROBE, 1008
WRITE_ALTER_NETLIST, 1008
Simulator Compatibility
COMPMOD, 950
COMPNET, 950
MOTOROLA, 950
NOELDOSWITCH, 1021
USE_SPECTRE_CONSTANT, 950
SPICE Compatibility
SPI3ASC, 949
SPI3BIN, 949
SPI3NOCOMPLEX, 949
SPICEDC, 949
SPIOUT, 949
OPTYP option, 756, 1006
OR Gate
see Double, Triple and Multiple Input
Digital Gates
OSR option, 1017
OUT_ABSTOL option, 1013
OUT_REDUCE option, 1013
OUT_RELTOL option, 1013
OUT_RESOL option, 1006
OUT_SMP option, 1006
OUT_STEP option, 1006
Output Shortform (.PROBE), 838
Overview
of the .cir File Structure, 69

- P -

Parallel LCR Circuit Tutorial, 1342
Parallel Switched Capacitor Macromodel, 102, 501
Equations, 502
Parameters, 501
PARAM
.STEP, 893
PARAM_BEFORE_USE option, 956
Parameter Correlation, 575
Parameter declaration, 113
Parameter Extraction, 309, 376, 1041 to 1060
Parameter Names in Eldo, 71
Parameter Sweep
.DATA, 585
.STEP, 890
PARAMETRIC_ACTRAN option, 1006
PARAMOPT_NOINITIAL option, 981
Parasitics
effects, 617
elements, 617
PARHIER option, 956
PARTGATE_AMS_ALL option, 1019
Partition Netlist into Newton Blocks
(.NWBLOCK), 753

Partitioning netlists Newton Block accuracy

RELTOL, 753
voltage accuracy
VNTOL, 753
PARTVDD option, 1019
PARTVDD_AMS_ALL option, 1019
Pattern Function, 95, 332
PCS option, 968
PCSPERIOD option, 969
PCSSIZE option, 969
Peak Detector Macromodel, 99, 430
Parameters, 430
PEVFLY option, 959
PGATEDEF option, 989
Philips MOS 11 Level 1100 (Eldo Level 65 or MOSP11) MOSFET Model, 288
Philips MOS 11 Level 1100 (Eldo Level 69) MOSFET Model, 290

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Philips MOS 11 Level 1101 (Eldo Level 63 or MOSP11) MOSFET Model, 286
Philips MOS 20 Level 2001 (Eldo Level 71) MOSFET Model, 292
Philips MOS 9 (Level 59 or MOSP9) MOSFET Model, 283
Philips PSP (Level 70) MOSFET Model, 291
Piece-Wise-Linear Function, 95, 338, 567
PIVCHECK option, 969
PIVREL option, 969
PIVTOL option, 970
Plotting
of Bus Signals (.PLOTBUS), 827
of Simulation Results (.PLOT), 791
of Subcircuit Nodes, 304, 810, 851
Output, 791
Pole-Zero
Analysis (.PZ), 851
Cancellation by Threshold, 1123
Numerical Issues, 1126
Post-processor, 34, 851, 1121 to 1126
Dialogue of, 1122
Polynomial, non-linear
Capacitor model, 133
Inductor model, 140
Resistor model, 122
POST option, 1006
POST_DOUBLE option, 1007
Post-Processing Library (PPL), 559, 929, 1255 to 1283
Examples, 1260
Post-processors
Pole-Zero, 34, 851, 1121 to 1126
POW, 78
POWNEG0 option, 959
PPL (Post-Processing Library), 1255
Previously Simulated Results
Usage of (.LOAD), 698
Usage of (.USE), 926
Print Tabular Output File (.PRINTFILE), 835
Printer Paper
Setting Width of (.WIDTH), 938
PRINTFILE_FREQ_STEP option, 1007
PRINTFILE_STEP option, 1007
PRINTFILE_TIME_STEP option, 1007

Printing
of Bus Signals (.PRINTBUS), 832
of Bus Signals (.PROBEBUS), 848
Printing of Results (.PRINT), 830
PRINTLG option, 997
Prior Simulation Input (.CHRSIM), 569
PROBE option, 1013
PROBEOP option, 1013
PROBEOP2 option, 1014
PROBEOPX option, 1014
PSD computation (.DSPMOD), 625
PSF, 47
PSF option, 1014
PSF_ALL_FILES option, 1015
PSF_FULLNAME option, 1015
PSF_NODEVICE_NOISE option, 1014
PSF_SCALARDC option, 1014
PSF_VERSION option, 1014
PSF_WRITE_ALL option, 1015
PSFASCII option, 1015
PSOSC option, 970
PSP103 (Level 75) MOSFET Model, 295
PSTRAN option, 1017
Pulse Amplitude Modulator Macromodel, 98, 419
Characteristics, 420
Parameters, 419
Pulse Function, 95, 336
Pulse Width Modulator Macromodel, 99, 425
Characteristics, 426
Parameters, 425
PVAL (extract function), 653
PWL, 79, 80, 605, 606
PWR, 78

- Q -

QTRUNC option, 970
— R —
radix
test vector files, 921
RAILINDUCTANCE option, 989
RAILRESISTANCE option, 989
Ramping, 1080
.RAMP, 852
DC, 853

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Transient, 853
RANDMC option, 982
RATPRINT option, 970
RC Reduction Options, 993
RC Wire Model, 90, 150
REAL (Real part of complex number), 79
REDUCE option, 990
Reliability Model Parameter Declaration, 548
Reliability Simulation, 1253
RELTOL option, 753, 887, 970, 1101
RELTRUNC option, 971
RELVAR option, 971
Remove library name (.DEL), 610
REPEAT
.SAVE, 857
Replace Node Name (.EQUIV), 634
reserved keywords, 779
RESET_MULTIPLE_RUN option, 1010
Resistor Model, 89, 122, 128
.LOOP, 699
.SENS, 863
Parameters, 128
RESNW option, 990
Restart Simulation, 1080
.RESTART, 854
RF keywords, 779
RGND option, 982
RGNDI option, 982
RISE_TIME option, 977
RISING (extract function), 653
RMMINRVAL option, 990
RMOS option, 990
RMS (extract function), 653
RMV0 option, 960
ROUND (Value rounded to integer), 79
Running
Eldo from the Command Line, 41

- S -

S, Y, Z Parameter Extraction, 97, 309, 376, 1041 to 1060
output file specification (.FFILE), 667, 1045
Source Syntax, 376, 1041, 1042
Safe Operating Area
Setting, 872

Sample and Hold Macromodel, 99, 421
Parameters, 421
SAMPLE option, 971
Saturating Resistor Macromodel, 98, 395
Characteristics, 396
Parameters, 395
Save Simulation Run, 1080
.SAVE, 857
Save Simulation Run at Multiple Time Points (.TSAVE), 916

SAVETIME option, 1015
Sawtooth Waveform Generator Macromodel, 98
Parameters, 413
Scale Factors in Eldo, 73
SCALE option, 991
SCALEBSIM option, 991
SCALM option, 991
Scattering parameters, 1041
Schichman \& Hodges, 246
SC-Integrators \& LDI's, 493
SC—Schmitt Trigger Example, 1460
SDA option, 949
S-Domain Filter Model, 92, 297
Transfer Function, 297
SEARCH option, 1022
Second Order Delta Sigma Modulator
Example, 1477
SELECT, 80
Select Index
in Pole-Zero Post-processing, 1124
Semiconductor Resistor Model, 90, 156
Parameters, 156
Sensitivity Analysis
AC (.SENSAC), 865
DC (.SENS), 863
Sensitivity Analysis (.SENS)
Examples, 1366
Sensitivity Analysis (.SENSPARAM), 867
SEQ
.SAVE, 858
Serial Switched Capacitor Macromodel, 102, 503
Equations, 504
Parameters, 503

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Serial-parallel Switched Capacitor
Macromodel, 102, 505
Equations, 506
Parameters, 506
Set
Bus Signal (.SIGBUS), 880
Circuit Temperature (.TEMP), 88, 907
Printer Paper Width (.WIDTH), 938
Safe Operating Area (.SETSOA), 872
Set Reliability Model Key (Password), 871
Set title (.TITLE), 909
SGN, 78
Shortform of Output (.PROBE), 838
SHRINK_FACTOR option, 992
SIGMA (Sum of values), 80
SIGN, 78
Signal Monitoring Specifications
Used with .PROBE Only, 845
SIGTAIL option, 982
SIMUDIV option, 1007
Simulation
Accuracy
RELTOL, 1101
VNTOL, 974, 1101
ADiT parameter, 790
ANALOG parameter, 790
Counters, 86
Convergence Information, 87
Grounded Capacitors Information, 86
Matrix Information, 87
Newton Block Information, 87
Node \& Element Information, 86
Current Accuracy
ITOL, 966
ELDO parameter, 790
Interruption, 1084
Output
Plotting of, 791
Printing of, 830
Re-run Facility (.ALTER), 549
Restart, 1080
Restart (.RESTART), 854
Running, 36
Save, 1080
Saving of (.SAVE), 857

Simulation Start Time (.START_TIME), 889
Simulator
Commands, 519
Configuration (.OPTION), 771, 940
SIN (Sine of value), 78, 95, 344
Sine Function, 95, 344
Single Frequency FM Function, 95, 343
Single Output Level Detector Macromodel, 99, 433
SINH (Hyperbolic sine of value), 78
Sinusoidal Voltage Source (.SINUS), 884
Sizing Facility (.SOLVE), 887
SLEWRATE (extract function), 654
SLOPE (extract function), 654
SMABS (Absolute value), 80
SMMAX (Maximum value), 80
SMMIN (Minimum value), 80
S-Model, 1048
Applications, 1052
FBLOCK, 1054
Functionality, 1053
Implementation, 1051
Syntax, 1054
SMOOTH option, 1015
SMSGN (Signum value), 80
SMSIGN (Signum value), 80
SOIBACK option, 992
Source Description
Amplitude Modulation Function, 323
Current Controlled Current Source, 96, 358
Current Controlled Voltage Source, 97, 371
Exponential Function, 95, 325
Exponential Pulse With Bit Pattern
Function, 95, 348
Independent Current Source, 94, 317
Independent Voltage Source, 93, 310
Noise Function, 95, 327
Noise Table Function, 95, 330
Pattern Function, 95, 332
Piece-Wise-Linear Function, 95, 338
Piece-Wise-Linear Source (.CHRENT), 567
Pulse Function, 95, 336
S, Y, Z Parameter Extraction, 376
Sine Function, 95, 344

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Single Frequency FM Function, 95, 343
Trapezoidal Pulse With Bit Pattern
Function, 95, 346
Voltage Controlled Voltage Source, 95
Voltage/Expression Controlled Current Source, 96, 363
Voltage/Expression Controlled Voltage
Source, 350
Sources, 93 to 97, 307
SP (Eldo Level 67) MOSFET Model, 290
Spectre Compatibility, 1395 to 1410
Speed and Accuracy, 1061
SPI3ASC option, 949
SPI3BIN option, 949
SPI3NOCOMPLEX option, 949
SPICE, 940
SPICEDC option, 949
SPIOUT option, 949
SPLITC option, 971
SPMODLEV option, 992
Spot Noise Figure (.SNF), 885
SQRT (Square root of value), 78
SSC
see Two-port Stability Circles
Stability Circles
see Two-port Stability Circles
stacktrace file, 63
Staircase Waveform Generator Macromodel, 98, 411
Parameters, 411
Standard Deviation, 706
STARTSMP option, 971
STAT option, 1007
Statistical Experimental Design and Analysis, 1227
STATISTICAL option, 982
Statistical Parameter Declarations
(.PARAMDEX), 788

Statistics File
Content, 64
STEP option, 971
STMicroelectronics
Models, 1509
Version of Eldo, 1510
STOPONFIRSTERROR option, 960

STOSMITH (Smith function), 79
STRICT option, 960
String parameters in Eldo, 71
Stripline Models
see Microstrip Models
SUBALEV option, 961
Subcircuit
Definition (.SUBCKT), 898
Duplicate parameters (.SUBDUP), 904
Error Messages, 1432
File Insertion (.ADDLIB), 544
Instance Model, 93, 301
Nodes
Plotting of, 304, 810, 851
Warning Messages, 1450
Subcircuit Description Termination (.ENDS), 633
Subcircuits
Access of Nodes, 902
Access of Nodes from within, 73
SUBFLAGPAR option, 961
Subtractor Macromodel, 100, 444
Parameters, 444
Suppress
Comment Lines from an Output File (.NOCOM), 742

Netlist from an Output File (.NOTRC), 752
Sweeping of Parameters (.STEP), 890
Switch
.SENS, 863
Current Controlled Macromodel, 98, 404
Characteristics, 405
Parameters, 404
Ideal Single-Pole Multiple-Throw
Macromodel, 407
Parameters, 407
Noise Model, 1036
SC Macromodel, 102, 488
Equivalent Circuit, 489
Parameters, 490
Voltage Controlled Macromodel, 98, 401
Characteristics, 402
Parameters, 401
Switched Capacitor Macromodels, 101, 481
Applications, 512

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

Syntax
Errors, 1411
General aspects
Comment lines, 70
Component names, 71
Continuation lines, 70
Directives, 74
First line, 70
Model names, 73
Node name conventions, 72
Parameter names, 71
Reserved keywords, 72
Scale factors, 73
String parameters, 71
Values, 73
of Analog Macromodels, 97 to 100, 379 to 445
of Commands, 102 to 118,519 to 938
of Devices, 89 to 93, 119 to 304
of Digital Macromodels, 100, 447 to 466
of Eldo, 70 to 118
of Macromodels, 97 to 102, 379 to 445, 481 to 511
of Magnetic Macromodels, 101, 467 to 480
of Mixed Signal Macromodels, 101
of Sources, 93 to 97, 307 to 376
of Switched Capacitor Macromodels, 101, 481 to 518

T —
T Parameter, 88
TAN (Tangent of value), 78
TANH (Hyperbolic tangent of value), 78
TCROSS (extract function), 654
TEMP Variable, 89
.STEP, 893
TEMP_UNIT option, 982
TEMPCOUK option, 1008
TEMPER Variable, 89
Temperature
.TEMP, 88
Handling in Eldo, 88
T Parameter, 88
TEMP Parameter, 89
TEMPER Parameter, 89
TMAX option, 992

TMIN option, 992
TMOD Parameter, 88
TNOM Parameter, 88
test vector files, 918 to 924
comments, 921
keywords
CODEFILE, 920
END, 921
max, 921
UNITS, 920
radix, 921
Test Vector Files (.TVINCLUDE), 918
Test Vector Files (.VEC), 932
TFALL (extract function), 657
TFT Amorphous-Si (Level 64) MOSFET Model, 287
TFT Polysilicon (Level 62) MOSFET Model, 286
TGP, 822
THERMAL_NOISE option, 994
Three Input Digital Gates
see Triple Input Digital Gates
TIME
.SAVE, 857
TIMEDIV option, 1008
TIMESMP option, 972
Time-step
Fixed, 971
TINTEG (extract function), 654, 657
TIspice Compatibility, 1384 to 1394
TMAX option, 992
TMIN option, 992
TMOD Parameter, 88
TNOM option, 88, 129, 312, 319, 907, 983
TOPCELL (.TOPCELL), 910
Touchstone Data Format, 1058
TPD (extract function), 654
TPDDD (extract function), 656
TPDUD (extract function), 656
TPDUU (extract function), 656
TPIEEE option, 983
Track and Hold Macromodel, 99, 423
Parameters, 423
Transfer Function (.TF), 908
Transformer (Ideal) Macromodel, 480

## A B C DEFGHIJKLMNOPQRSTUVWXYZ

Transformer Winding Macromodel, 101, 468
Transformer with Variable Number of
Windings Macromodel, 101, 478
Transient Analysis (.TRAN), 911
.CHRSIM, 569
.CONSO, 574
.IC, 682
.LOOP, 699
.MC, 706
.PRINT, 802
Examples, 1345, 1356, 1359, 1460, 1461, $1467,1469,1472,1477,1480$
Switch Macromodel, 488
Transient Noise Analysis, 1023
.NOISETRAN, 747
Transmission Line Model, 90, 163
TRAP option, 1015
Trapezoidal Pulse With Bit Pattern Function (PBIT), 95
Triangle Waveform Generator Macromodel, 98, 415
Parameters, 415
Triangular to Sine Wave Converter Macromodel, 98, 409
Characteristics, 410
Parameters, 409
Triple Input AND Gate Macromodel, 100
Triple Input Digital Gates, 100, 459
Triple Input NAND Gate Macromodel, 100
Triple Input NOR Gate Macromodel, 100
Triple Input OR Gate Macromodel, 100
TRISE (extract function), 657
Trouble Shooting, 1457
TRTOL option, 972
TRUNC (Truncated value), 79
TUNING option, 972
Tutorials, 1341
1—Parallel LCR Circuit, 1342
2-4th Order Butterworth Filter, 1345
3-Band Pass Filter, 1349
4-Low Pass Filter, 1353
5-Colpitts Oscillator, 1356
6-High Voltage Cascade, 1359
7-Non-inverting Amplifier, 1363
8—Bipolar Amplifier, 1366, 1369

Two Input Digital Gates see Double Input Gates
Two-port Constant Gain Circles
GAC, 820
GPC, 821
Two-port Gain Extract, 821
Available Power Gain
GA, 821
GAM, 821
GASM, 821
GAUM, 822
GP, 822
TGP, 822
Two-port Noise Circles NC, 820
Two-port Noise Parameters, 819
BOPT, 819
GOPT, 819
NFMIN, 819
RNEQ, 819
Two-port Stability Circles, 822 LSC, 823 SSC, 822
Two-port Stability Factors BFACTOR, 818
KFACTOR, 818
MUFACTOR, 818
MUFACTOR_L, 818
MUFACTOR_S, 819
— U -
UDMP, 255
UIC Parameter, 135, 672, 682
ULOGIC option, 983
UNBOUND option, 973
UNITS statement in test vector files, 920
Unswitched Capacitor Macromodel, 102, 510
Equations, 511
Parameters, 510
Usage of FAS Macromodels, 380
Use Previously Simulated Results
.LOAD, 698
.USE, 926
Use Reliability Model Key (Password), 928
Use Tcl File
.USE_TCL, 929, 1255

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

USE_LOCATION_MAP option, 961
USE_SPECTRE_CONSTANT option, 950
USEDEFAP option, 992
USEFIRSTDEF option, 962
User Defined Distributions (Monte Carlo)
(.DISTRIB), 614

User Defined Function (.FUNC), 675
USETHREAD option, 962
Utilities, 1495
— V —
VALAT (extract function), 657
Value Tables (.TABLE), 905
Values in Eldo, 73
VAMAXEXP option, 1022
VBCSAT option, 1008
VBIC v1.1.5 Model, 239
Parameters, 239
VBIC v1.2 Model, 238
Parameters, 239
vcd2tv utility, 1496
VERBOSE option, 997
Verilog-A
Compile and Load Modules (.HDL), 678
Compile and Load Modules (.VERILOG), 933
Load Compiled Modules (.USE_VERILOGA), 931

VMAX option, 973
VMIN option, 973
VNTOL, 753, 1101
Correct usage, 1457
VNTOL option, 974
Voltage Controlled Oscillator (VCO)
Macromodel, 99, 428
Parameters, 428
Voltage Controlled Switch Macromodel, 98, 401
Parameters, 401
Voltage Controlled Voltage Source, 95
Voltage Limiter Macromodel, 98, 397
Parameters, 397, 399
Voltage loop, 953, 962
Voltage Source
Sinusoidal (.SINUS), 884

Voltage/Expression Controlled Current Source, 363
Voltage/Expression Controlled Voltage
Source, 350
VOLTAGE_LOOP_SEVERITY option, 962
VXPROBE option, 1008
— W —
WARN option, 997
WARN2ERR option, 962
Warning Messages, 1411, 1436
Global, 1436
Miscellaneous, 1450
Related to Commands, 1443
Related to Models, 1448
Related to Nodes, 1439
Related to Objects, 1440
Related to Subcircuits, 1450
Warnings
.SETSOA, 872 to 879
Messages, 1411
WARNMAXV option, 992, 993
Waveform Definition (.DEFWAVE), 605
Waveform Definition Using a Tcl Function .TCL_WAVE, 906
WBULK option, 997
WDF option, 1015
WFREQ (extract function), 658
WINTEG (extract function), 658
WL option, 993
Worst Case Analysis (.WCASE), 934
.MC, 707
WRITE_ALTER_NETLIST option, 1008
WSF option, 949
WSFASCII option, 949

- X -

XA option, 974
XBYNAME option, 962
XCOMPRESS (extract function), 659
XDOWN (extract function), 659
XMAX (extract function), 659
XMIN (extract function), 659
XTHRES (extract function), 660
XUP (extract function), 660
XYCOND (extract function), 660

## ABCDEFGHIJKLMNOPQRSTUVWXYZ

- Y -

YMFACT option, 993
YTOSMITH (Smith function), 79
YVAL (extract function), 661

## - Z -

ZCHAR option, 1022
Z-Domain Filter Model, 92, 299
Transfer Function, 299
Z-Domain Representation of SC Macromodels, 491
ZOOMTIME option, 983
ZTOSMITH (Smith function), 79

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5.1. Customer may copy Software only as reasonably necessary to support the authorized use. Each copy must include all notices and legends embedded in Software and affixed to its medium and container as received from Mentor Graphics. All copies shall remain the property of Mentor Graphics or its licensors. Customer shall maintain a record of the number and primary location of all copies of Software, including copies merged with other software, and shall make those records available to Mentor Graphics upon request. Customer shall not make Software available in any form to any person other than Customer's employees and on-site contractors, excluding Mentor Graphics competitors, whose job performance requires access and who are under obligations of confidentiality. Customer shall take appropriate action to protect the confidentiality of Software and ensure that any person permitted access does not disclose or use it except as permitted by this Agreement. Log files, data files, rule files and script files generated by or for the Software (collectively "Files") constitute and/or include confidential information of Mentor Graphics. Customer may share Files with third parties excluding Mentor Graphics competitors provided that the confidentiality of such Files is protected by written agreement at least as well as Customer protects other information of a similar nature or importance, but in any case with at least reasonable care. Standard Verification Rule Format ("SVRF") and Tcl Verification Format ("TVF") mean Mentor Graphics' proprietary syntaxes for expressing process rules. Customer may use Files containing SVRF or TVF only with Mentor Graphics products. Under no circumstances shall Customer use Software or allow its use for the purpose of developing, enhancing or marketing any product that is in any way competitive with Software, or disclose to any third party the results of, or information pertaining to, any benchmark. Except as otherwise permitted for purposes of interoperability as specified by applicable and mandatory local law, Customer shall not reverse-assemble, reverse-compile, reverseengineer or in any way derive from Software any source code.
5.2. Customer may not sublicense, assign or otherwise transfer Software, this Agreement or the rights under it, whether by operation of law or otherwise ("attempted transfer"), without Mentor Graphics' prior written consent and payment of Mentor Graphics' then-current applicable transfer charges. Any attempted transfer without Mentor Graphics' prior written consent shall be a material breach of this Agreement and may, at Mentor Graphics' option, result in the immediate termination of the Agreement and licenses granted under this Agreement. The terms of this Agreement, including without limitation the licensing and assignment provisions, shall be binding upon Customer's permitted successors in interest and assigns.
5.3. The provisions of this Section 5 shall survive the termination of this Agreement.
6. SUPPORT SERVICES. To the extent Customer purchases support services for Software, Mentor Graphics will provide Customer with available updates and technical support for the Software which are made generally available by Mentor Graphics as part of such services in accordance with Mentor Graphics' then current End-User Software Support Terms located at http://supportnet.mentor.com/about/legal/.

## 7. LIMITED WARRANTY.

7.1. Mentor Graphics warrants that during the warranty period its standard, generally supported Software, when properly installed, will substantially conform to the functional specifications set forth in the applicable user manual. Mentor Graphics does not warrant that Software will meet Customer's requirements or that operation of Software will be uninterrupted or error free. The warranty period is 90 days starting on the 15 th day after delivery or upon installation, whichever first occurs. Customer must notify Mentor Graphics in writing of any nonconformity within the warranty period. For the avoidance of doubt, this warranty applies only to the initial shipment of Software under the applicable Order and does not renew or reset, by way of example, with the delivery of (a) Software updates or (b) authorization codes or alternate Software under a transaction involving Software re-mix. This warranty shall not be valid if Software has been subject to misuse, unauthorized modification or improper installation. MENTOR GRAPHICS' ENTIRE LIABILITY AND CUSTOMER'S EXCLUSIVE REMEDY SHALL BE, AT MENTOR GRAPHICS' OPTION, EITHER (A) REFUND OF THE PRICE PAID UPON RETURN OF SOFTWARE TO MENTOR GRAPHICS OR (B) MODIFICATION OR REPLACEMENT OF SOFTWARE THAT DOES NOT MEET THIS LIMITED WARRANTY, PROVIDED CUSTOMER HAS OTHERWISE COMPLIED WITH THIS AGREEMENT. MENTOR GRAPHICS MAKES NO WARRANTIES WITH RESPECT TO: (A) SERVICES; (B) SOFTWARE WHICH IS LICENSED AT NO COST; OR (C) BETA CODE; ALL OF WHICH ARE PROVIDED "AS IS."
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9. LIFE ENDANGERING APPLICATIONS. NEITHER MENTOR GRAPHICS NOR ITS LICENSORS SHALL BE LIABLE FOR ANY DAMAGES RESULTING FROM OR IN CONNECTION WITH THE USE OF SOFTWARE IN ANY APPLICATION WHERE THE FAILURE OR INACCURACY OF THE SOFTWARE MIGHT RESULT IN DEATH OR PERSONAL INJURY. THE PROVISIONS OF THIS SECTION 9 SHALL SURVIVE THE TERMINATION OF THIS AGREEMENT.
10. INDEMNIFICATION. CUSTOMER AGREES TO INDEMNIFY AND HOLD HARMLESS MENTOR GRAPHICS AND ITS LICENSORS FROM ANY CLAIMS, LOSS, COST, DAMAGE, EXPENSE OR LIABILITY, INCLUDING ATTORNEYS' FEES, ARISING OUT OF OR IN CONNECTION WITH CUSTOMER'S USE OF SOFTWARE AS DESCRIBED IN SECTION 9. THE PROVISIONS OF THIS SECTION 10 SHALL SURVIVE THE TERMINATION OF THIS AGREEMENT.

## 11. INFRINGEMENT.

11.1. Mentor Graphics will defend or settle, at its option and expense, any action brought against Customer in the United States, Canada, Japan, or member state of the European Union which alleges that any standard, generally supported Software product infringes a patent or copyright or misappropriates a trade secret in such jurisdiction. Mentor Graphics will pay any costs and damages finally awarded against Customer that are attributable to the action. Customer understands and agrees that as conditions to Mentor Graphics' obligations under this section Customer must: (a) notify Mentor Graphics promptly in writing of the action; (b) provide Mentor Graphics all reasonable information and assistance to settle or defend the action; and (c) grant Mentor Graphics sole authority and control of the defense or settlement of the action.
11.2. If a claim is made under Subsection 11.1 Mentor Graphics may, at its option and expense, (a) replace or modify Software so that it becomes noninfringing, or (b) procure for Customer the right to continue using Software, or (c) require the return of Software and refund to Customer any license fee paid, less a reasonable allowance for use.
11.3. Mentor Graphics has no liability to Customer if the claim is based upon: (a) the combination of Software with any product not furnished by Mentor Graphics; (b) the modification of Software other than by Mentor Graphics; (c) the use of other than a current unaltered release of Software; (d) the use of Software as part of an infringing process; (e) a product that Customer makes, uses, or sells; (f) any Beta Code; (g) any Software provided by Mentor Graphics' licensors who do not provide such indemnification to Mentor Graphics' customers; or (h) infringement by Customer that is deemed willful. In the case of (h), Customer shall reimburse Mentor Graphics for its reasonable attorney fees and other costs related to the action.
11.4. THIS SECTION IS SUBJECT TO SECTION 8 ABOVE AND STATES THE ENTIRE LIABILITY OF MENTOR GRAPHICS AND ITS LICENSORS AND CUSTOMER'S SOLE AND EXCLUSIVE REMEDY WITH RESPECT TO ANY ALLEGED PATENT OR COPYRIGHT INFRINGEMENT OR TRADE SECRET MISAPPROPRIATION BY ANY SOFTWARE LICENSED UNDER THIS AGREEMENT.

## 12. TERM.

12.1. This Agreement remains effective until expiration or termination. This Agreement will immediately terminate upon notice if you exceed the scope of license granted or otherwise fail to comply with the provisions of Sections 2, 3, or 5. For any other material breach under this Agreement, Mentor Graphics may terminate this Agreement upon 30 days written notice if you are in material breach and fail to cure such breach within the 30 day notice period. If a Software license was provided for limited term use, such license will automatically terminate at the end of the authorized term.
12.2. Mentor Graphics may terminate this Agreement immediately upon notice in the event Customer is insolvent or subject to a petition for (a) the appointment of an administrator, receiver or similar appointee; or (b) winding up, dissolution or bankruptcy.
12.3. Upon termination of this Agreement or any Software license under this Agreement, Customer shall ensure that all use of the affected Software ceases, and shall return it to Mentor Graphics or certify its deletion and destruction, including all copies, to Mentor Graphics' reasonable satisfaction.
12.4. Termination of this Agreement or any Software license granted hereunder will not affect Customer's obligation to pay for products shipped or licenses granted prior to the termination, which amounts shall immediately be payable at the date of termination.
13. EXPORT. Software is subject to regulation by local laws and United States government agencies, which prohibit export or diversion of certain products, information about the products, and direct products of the products to certain countries and certain persons. Customer agrees that it will not export Software or a direct product of Software in any manner without first obtaining all necessary approval from appropriate local and United States government agencies.
14. U.S. GOVERNMENT LICENSE RIGHTS. Software was developed entirely at private expense. All Software is commercial computer software within the meaning of the applicable acquisition regulations. Accordingly, pursuant to US FAR 48 CFR 12.212 and DFAR 48 CFR 227.7202, use, duplication and disclosure of the Software by or for the U.S. Government or a U.S. Government subcontractor is subject solely to the terms and conditions set forth in this Agreement, except for provisions which are contrary to applicable mandatory federal laws.
15. THIRD PARTY BENEFICIARY. Mentor Graphics Corporation, Mentor Graphics (Ireland) Limited, Microsoft Corporation and other licensors may be third party beneficiaries of this Agreement with the right to enforce the obligations set forth herein.
16. REVIEW OF LICENSE USAGE. Customer will monitor the access to and use of Software. With prior written notice and during Customer's normal business hours, Mentor Graphics may engage an internationally recognized accounting firm to review Customer's software monitoring system and records deemed relevant by the internationally recognized accounting firm to confirm Customer's compliance with the terms of this Agreement or U.S. or other local export laws. Such review may include FLEXIm or FLEXnet (or successor product) report log files that Customer shall capture and provide at Mentor Graphics' request. Customer shall make records available in electronic format and shall fully cooperate with data gathering to support the license review. Mentor Graphics shall bear the expense of any such review unless a material non-compliance is revealed. Mentor Graphics shall treat as confidential information all information gained as a result of any request or review and shall only use or disclose such information as required by law or to enforce its rights under this Agreement. The provisions of this section shall survive the termination of this Agreement.
17. CONTROLLING LAW, JURISDICTION AND DISPUTE RESOLUTION. The owners of the Mentor Graphics intellectual property rights licensed under this Agreement are located in Ireland and the United States. To promote consistency around the world, disputes shall be resolved as follows: This Agreement shall be governed by and construed under the laws of the State of Oregon, USA, if Customer is located in North or South America, and the laws of Ireland if Customer is located outside of North or South America. All disputes arising out of or in relation to this Agreement shall be submitted to the exclusive jurisdiction of Portland, Oregon when the laws of Oregon apply, or Dublin, Ireland when the laws of Ireland apply. Notwithstanding the foregoing, all disputes in Asia (except for Japan) arising out of or in relation to this Agreement shall be resolved by arbitration in Singapore before a single arbitrator to be appointed by the Chairman of the Singapore International Arbitration Centre ("SIAC") to be conducted in the English language, in accordance with the Arbitration Rules of the SIAC in effect at the time of the dispute, which rules are deemed to be incorporated by reference in this section. This section shall not restrict Mentor Graphics' right to bring an action against Customer in the jurisdiction where Customer's place of business is located. The United Nations Convention on Contracts for the International Sale of Goods does not apply to this Agreement.
18. SEVERABILITY. If any provision of this Agreement is held by a court of competent jurisdiction to be void, invalid, unenforceable or illegal, such provision shall be severed from this Agreement and the remaining provisions will remain in full force and effect.
19. MISCELLANEOUS. This Agreement contains the parties' entire understanding relating to its subject matter and supersedes all prior or contemporaneous agreements, including but not limited to any purchase order terms and conditions. Some Software may contain code distributed under a third party license agreement that may provide additional rights to Customer. Please see the applicable Software documentation for details. This Agreement may only be modified in writing by authorized representatives of the parties. All notices required or authorized under this Agreement must be in writing and shall be sent to the person who signs this Agreement, at the address specified below. Waiver of terms or excuse of breach must be in writing and shall not constitute subsequent consent, waiver or excuse.

Rev. 090402, Part No. 239301


[^0]:    1. Refer to the EXP, PATTERN, PULSE, PWL, SFFM and SIN source functions.
[^1]:    .AGEMODEL MODEL=model_name [parameter=value]

[^2]:    (1)

    Further information, and equations of the Diffusion resistor model, can be found on the Philips website:
    http://www.nxp.com/acrobat_download/other/philipsmodels/resistor.pdf

[^3]:    (i)

    For model parameters, please refer to the Diode Model Level 21 Parameters of the Eldo Device Equations Manual.

[^4]:    ## Note

    Eldo defaults LMIN and WMIN to $1 \times 10^{-6} \mathrm{~m}$ if the user did not specify these parameters. To avoid mistakes in finding the correct models, please set the LMIN and WMIN values in your model cards.

[^5]:    i) See "S, Y, Z Parameter Extraction" on page 376.

[^6]:    1. Refer to the EXP, PATTERN, PULSE, PWL, SFFM and SIN source functions.
[^7]:    1. Refer to the EXP, PULSE, PWL, SFFM and SIN source functions.
[^8]:    ©
    For further information on FAS models, please refer to the CFAS User's Manual.

[^9]:    1
    For more information, refer to the ".MODEL" on page 723.

[^10]:    (1)

    For more information on these functions, refer to ".EXTRACT" on page 637.

[^11]:    Last Simulation

[^12]:    .MODEL-Model definition
    .NOISE-Noise analysis

[^13]:    1. HSPICE is a registered trademarks of Synopsys, Inc.
